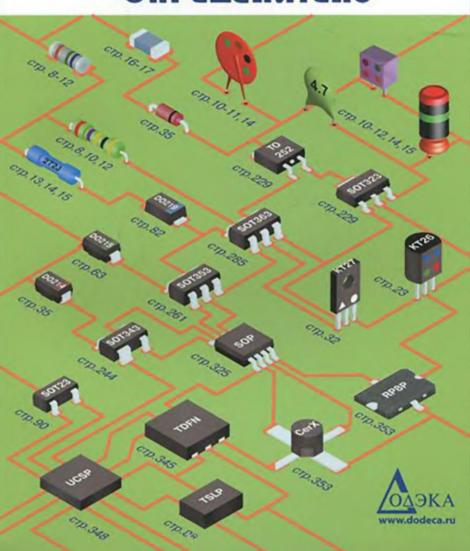
МАРКИРОВКА ЭЛЕКТРОННЫХ КОМПОНЕНТОВ ОПРЕДЕЛИТЕЛЬ





MAPHUPOBHA EMENTPOHNUX MOMPOHENTOB

ОПРЕДЕЛИТЕЛЬ

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Книга представляет собой справочник-определитель электронных компонентов по их внешнему виду. Пользуясь данным справочником, можно расшифровать кодовую или цветовую маркировку большинства пассивных (реаисторы, конденсаторы, катушки индуктивности) и активных (дискретные компоненты и микросхемы) электронных компонентов отечественного и импортного производства. Справочные материалы приведены в графической и табличной форме.

Поиск в определителе осуществляется по типу корпуса компонента, а далее по типу маркировки: цветовой или кодовой. Справочник содержит более 15000 кодовых маркировох актиеных компонентов: диодов, динисторов, стабилитронов, биполярных и полевых транзисторов, ключей, усилителей, компараторов, шифровых потенциометров, цифроаналоговых и аналогоцифровых преобразователей, вентилей и т.п. в корпусах для поверхностного монтажа, включая такие корпуса, как SOD, SOT, MSOP, TQFN, UCSP. На все компоненты приводится справочная информация о функциональном назначении приборов, фирме-производителе, основных характеристиках и особенностях, а также цоколевке выводов. В отдельных главах приведены подробные сведения по цветовой и кодовой маркировке отечественных компонентов в корпусах типа КТ-26 и КТ-27.

В главах, посвященным пассивным компонентам, рассмотрены принципы цветовой и кодовой маркировки резисторов, конденсаторов, катушек индуктивности и других элементов по номиналу, допускам и другим параметрам, а также нестандартная маркировка компонентов некоторых ведущих фирм-производителей.

Книга предназначена для широкого круга радиолюбителей и радиоинженеров.

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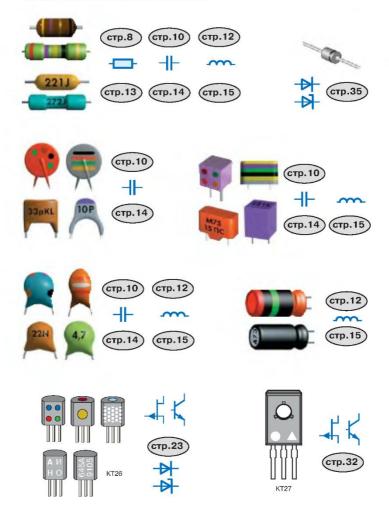
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СОДЕРЖАНИЕ

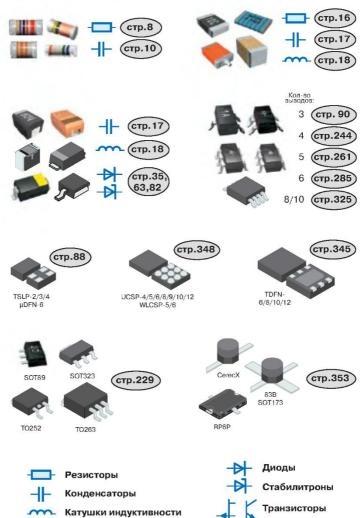
навигатор по внешнему виду компонентов	
Корпуса для монтажа в отверстия	
Корпуса для поверхностного монтажа	!
Общие правила маркировки	
Это необходимо знать	
Цветовая маркировка пассивных компонентов	'
Символьная маркировка пассивных компонентов	'
Цифровая маркировка пассивных компонентов	
Цветовая маркировка резисторов	
Цветовая маркировка конденсаторов	
Цветовая маркировка катушек индуктивности	13
Кодовая маркировка выводных резисторов	
Кодовая маркировка выводных конденсаторов	1
Кодовая маркировка выводных катушек индуктивности	1
Маркировка резисторов для поверхностного монтажа	10
Маркировка конденсаторов для поверхностного монтажа	1
Маркировка индуктивностей для поверхностного монтажа	1
Таблицы соответствия	19
Ряды номинальных значений по EIA	
Маркировка отечественных п/п приборов в корпусе КТ-26 (ТО-92)	2
История	2
Общие принципы маркировки	2
Типы маркировки полупроводниковых приборов	2
Цифро-буквенная маркировка	
Цветовая четырехточечная маркировка	
Символьно-цветовая маркировка	2
Цветовая двухточечная маркировка	2
Символьно-буквенная маркировка	
Нестандартизируемая маркировка	
Маркировка отечественных п/п приборов в корпусе КТ-27 (ТО-126)	3
Маркировка п/п компонетов для поверхностного монтажа	
Назначение колонок в таблицах	
SOD66/91	
SOD110, DO214, SMA/B/C	
SOD123/323, DO215/216	
SOD523/623/723, DO219, SMF	
SOT883, TSLP, µDFN	
SOT23-3, SOT323/523	
SOT89/223, TO252/263	
SOT143/343	
SOT23-5, SOT353/553	
SOT23-6, SOT363/563	
MSOP/SOP-8/10	
LFCSP, TDFN, TQFN.	
UCSP. WCSP	
SOT173	
Размеры корпусов для поверхностного монтажа	
Список фирм-производителей.	
Список фирм-производителей. Список сокращений и условных обозначений.	36
Список сокращении и условных осозначении Список обозначений функции прибора.	
Таблица соответствия обозначений наиболее полупярных корпусов	

НАВИГАТРОР ПО ВНЕШНЕМУ ВИДУ КОМПОНЕНТОВ

Корпуса для монтажа в отверстия



Корпуса для поверхностного монтажа



ОБЩИЕ ПРАВИЛА МАРКИРОВКИ

Это необходимо знать

Для того чтобы правильно воспринимать и использовать материал, прадставленный в этой книге, необходимо ознакомиться со следуюшей информацией.

Очень важны размеры корпусов, поскольку внешне многие корпуса пожожи друг на друга, а для идентификации прибора необходимо знать не только маркировку, но и тип корпуса. Но и это может не спасти. Так, корпус типа SOD-80 у фирмы Philips имеет диаметр 1.6 мм (ном.), а корпус с таким же названием у ряда других фирм имеет диаметр 1.4 мм, что даже меньше диаметра другого, более компактного, корпуса фирмы Philips SOD-80C. Корпус типа SOD-15 фирмы SGS-Тhотмол очень похож на корпуса 7043 и SMC, но не совпадает с ними по установочным размерам.

Возможны ситуации, когда фирмы-производители в одном и том же корпусе под одной и той же маркировкой выпускают разные приборы. Например, фирма Philips выпускает в корпусе SOT-323 n-p-n-транзистор BC818W и маркирует его кодом 6H, а фирма Motorola в таком же корпусе с той-же маркировкой 6H помещает p-n-p-транзистор MUN5131T1. Такая же ситуация встречается и внутри одной фирмы. Например, у фирмы Siemens в корпусе SOT-23 под маркировкой 1A выпускаются транзисторы BC846A и SMBT3904, имеющие разные параметры. Различить такие приборы, установленные на плате, можно только по окружающим их компонентам и, соответственно, схеме включения.

Путаница существует не только с маркировкой, но и цоколевкой корпусов. Например, корпус типа SOT-89 у фирм Rohm, Siemens, Toshiba имеет цоколевку 1-2-3 (вид сверху), а у Philips этот же корпус имеет цоколевку 2-3-1 или 3-2-1. В данной книге номера выводов и их функциональное значение у разных фирм приведены к единой системе.

Не лучше ситуация и с пассивными компонентами для поверхностного монтажа. Если на корпусе стоит маркировка 103, то это может быть резистор номиналом 10 кОм, конденсатор емкостью 10 нФ или индуктивность 10 мГн. Если на корпусе стоит маркировка 2R2, то это может быть и резистор номиналом 2.2 Ом, и конденсатор емкостью 2.2 пФ. Код 107 может означать 0.1 Ом (Philips) или 100 мкФ (Panasonic).

В корпусах типа 0603, 0805 и т.п. без маркировки могут находиться конденсатор, индуктивность или резистор-перемычка (Zero-Ohm, jumper).

Цветная полоса или выемка-ключ на корпусах типа SOD-123, DO-215 может указывать на катод диода или вывод «плюс» у электролитического конденсатора.

По внешнему виду очень трудно отличить друг от друга R, С и L, если они находятся в цилиндрических корпусах с выводами и маркирукотся цветными кольцами. Но и после идентификации могут возникнуть сложности с определением параметров компонента. Например, на практике для цветовой маркировки постоянных конденсаторов используются несколько методик (см. главу «Конденсаторы. Цветовая маркировка»).

В одинаковых корпусах с одинаковым цветовым кодом может выпускаться целая серия приборов с разными параметрами. Например, фирма Motorola выпускает в корпусе типа SOD-80, маркируемом одним цветным кольцом, целую серию стабилитронов (51 прибор) с напряжением стабилизации от 1.8 до 100 В и током от 0.1 до 1.7 А. В таком же корпусе фирма Philips выпускает серию диодов.



SOD80



SOD15



7343



SOT323



BC818W (Philips) MVN5131T1 (Motorola)

SOT23



BC846A (Siemens) SMBT3904 (Siemens)

SOD123



Конденсатор — **⊕** Диод — катод Стабилитрон — катод



Необходимо правильно определять сам цвет маркировки. На практике могут встречаться сложности с различием следующих оттенков: серый — се. голубой — серебристый; голубой — бирюзовый — электрик: желтый — золотистый: оранжевый — св. коричневый — табачный — бежевый.

Черное кольцо посередине корпуса имеют не только резисторы-перемычки (Zero-Ohm, jumper), но и другие приборы, особенно с учетом технологического разброса при нанесении маркировки.

Многие фирмы, помимо принципов маркировки, указанных в публикациях Международной Электротехнической Комиссии (IEC), используют свою внутрифирменную цветовую и кодовую маркиров-ки. Например, встречается маркировка SMD-резисторов, когда вместо цифры 8 ставится двоеточие. В таких случаях маркировка 1:23 означает 182 кОм, а :0R6 — 80.6 Ом.

SOT (SOD) — Small Outline Transistor (Diode) — в дословном переводе означает «малогабаритный транзистор (диод)». На современном этапе в корпуса типа SOT помещают не только транзисторы и диоды, но и транзисторы с резисторами, стабилитроны, стабилизаторы напряжения на базе операционного усилителя и многое другое, а количество выводов может быть более трех. Органы стандартизации не успевают за новыми разработками фирм, и те вынуждены вводить свои новые обозначения, которые представлены в «Сводной таблице корпусов».

Цветовая маркировка пассивных компонентов

В соответствии с ГОСТ175-72 и требованиями Публикации 62 IEC цветовая маркировка наносится в виде 3, 4, 5 или 6 цветных колец. Маркировочные кольца должны быть сдвинуты к одному из выводов или ширина первого или второго кольца должна быть в два раза больше других, что на практике выдерживается не всегда. Вместо цветовых колец могут использоваться цветовые точки.

При маркировки конденсаторов тремя кольцами допуск равен 20%; возможно сочетание двух колец и точки, указывающей на множитель. При маркировки пятью кольцами цвет корпуса указывает на значение рабочего напряжения. В полярных конденсаторах положительный вывод отмечается точкой или выводом большего диаметра.

Для индуктивностей кодируется номинальное значение индуктивности и допуск, т.е. допускаемое отклонение от указанного номинала. Наиболее часто применяется кодировка 4 или 3 цветными кольцами или точками. Первые две метки указывают на значение номинальной индуктивности в микрогенри (мкГн), третья метка — множитель, четвертая — допуск. В случае кодирования 3 метками подразумевается допуск 20%. Цветное кольцо, обозначающее первую цифру номинала, может быть шире, чем все остальные.

Символьная маркировка пассивных компонентов

При символьной маркировке используются 2 или 3 цифры в сочетании с символом, расположенным на месте десятичной точки и обозначающим единицу измерения.

После номинала может указываеться допуск и ТКЕ. Отсутствие маркировки допуска обычно означает допуск по умолчанию $\pm 20\%$. Для конденсаторов дополнительно может указываться рабочее напряжение, символьное обозначение которого обычно размещается в начале, перед номиналом.

Иногда применяется непосредственная маркировка номинала без указания множителя. В этом случае надпись «680К» на индуктивности будет означать не 68 мкГн ±10% (в соответствии со стандаютной маркировкой), а 680 мкГн ±10%.

Помимо вышеназванных параметров на корпус может наноситься дополнительная кодированная информация, например о дате выпуска, типе, номинальной мощности и т.д.

Цифровая маркировка пассивных компонентов

При этом способе используются 3 или 4 цифры, последняя из которых обозначает количество нулей, добавляемых к стоящим впереди цифрам. Исключение составляют цифры 7, 8 и 9 для сопротивлений и цифра 9 для конденсаторов, обозначающие множитель в соответствии с приведенной ниже таблицей. Полученное значение равно номиналу в Ом для сопротивлений, пФ для емкостей и мкГн для индуктивностей. Для электролитических конденсаторов номинальное значение обычно дается сразу в мкФ. При использовании 2 цифр номинальное значение берется из ряда Е24 и имеет допуск 5% и более, при 3 цифрах номинальное значение берется из ряда Е96 и имеет допуск 1% и менее.

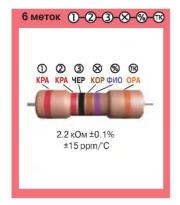
Кроме стандартных способов маркировки используются и нестандартные, часть из которых приведена в примерах.

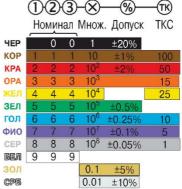
ЦВЕТОВАЯ МАРКИРОВКА РЕЗИСТОРОВ











Нестандартная маркировка

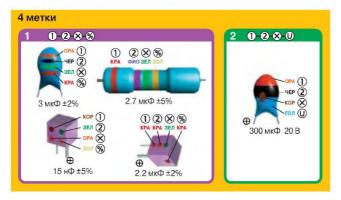




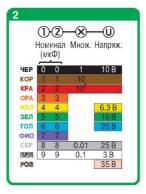


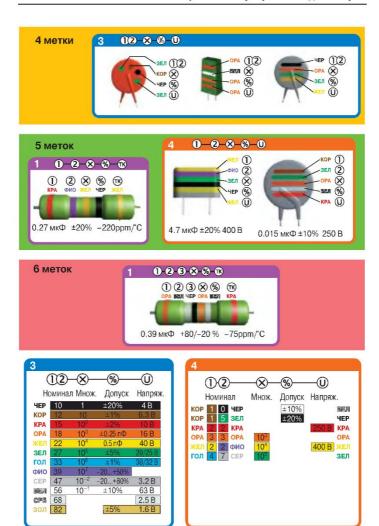
ЦВЕТОВАЯ МАРКИРОВКА КОНДЕНСАТОРОВ



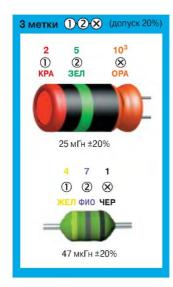




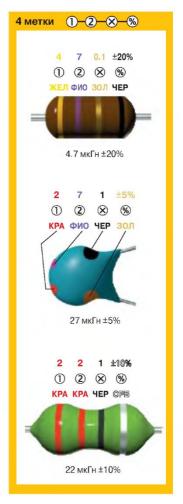




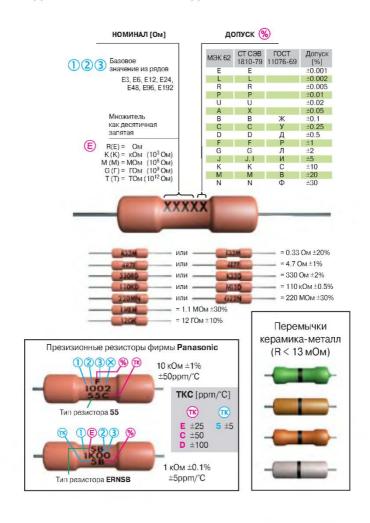
ЦВЕТОВАЯ МАРКИРОВКА КАТУШЕК ИНДУКТИВНОСТИ







КОДОВАЯ МАРКИРОВКА ВЫВОДНЫХ РЕЗИСТОРОВ



КОДОВАЯ МАРКИРОВКА ВЫВОДНЫХ КОНДЕНСАТОРОВ









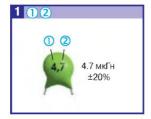
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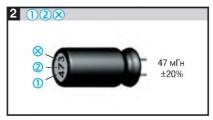
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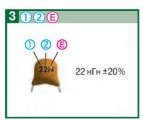
%	%	
В	Ж	±0.1
C	У	±0.25
D	Д	±0.5
F	P	±1
G	Л	±2
J	И	±5
K	C	±10
M	В	±20
N	Ф	±30
Q	0	-10+30
Т	Э	-10+50
Y	Ю	-10+100
S	Б	-20+50
Z	A	-20+80

rke [ppm/°C]
TK	TK
A	П100
В	H10
C	МПО
D	H30
E	H70
F	H90
н	M33
K	M2200
L	M75
N	П33
Р	M150
R	M220
S	П330
Ţ	M470
U	M750
V	M1500
X	H50
Z	H20

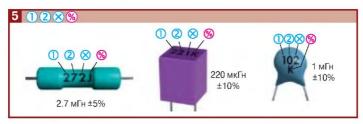
КОДОВАЯ МАРКИРОВКА ВЫВОДНЫХ КАТУШЕК ИНДУКТИВНОСТИ













МАРКИРОВКА РЕЗИСТОРОВ ДЛЯ ПОВЕРХНОСТНОГО МОНТАЖА







123 Номинал [Ом]: 0...9 Множитель:
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Е Десятичная точка: **R**

Перемычки (Jamper-Chip) R < 50 мОм

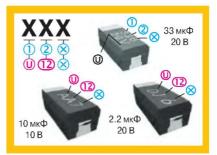


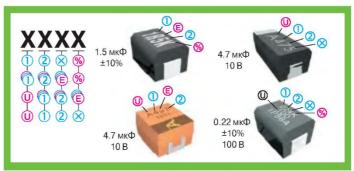




МАРКИРОВКА КОНДЕНСАТОРОВ ДЛЯ ПОВЕРХНОСТНОГО МОНТАЖА







- Рабочее напряжение:G 4
 - J-6.3/7 D-20 A-10 E-25 C-16 V-35
- Рабочее напряжение:0...9 величинаV вольты
- Е Десятичная точка и единица измерения: µ — мкФ R — мкФ
- Множитель: (12) Номинал [пф]: A - 1.0M - 3.0Y - 8.2 -0.1B - 11N - 3.3z - 9.1- 1 P - 3.6C - 1.2a - 2.5- 10 D - 1.3Q - 3.9b - 3.5 -10^{2} E - 1.5 R - 4.3d - 4.0 -10^{3} F - 1.65 - 4.7e - 4.5 -10^4 G - 1.8T - 5.1 f - 5.0H - 2.0U - 5.6 5 -10^{5} m - 6.06 -10^{6} J - 2.2V - 6.2n - 7.0

t - 8.0

q - 9.0

П2 Номинал: (12⊗ — [пф]) 0...9

W - 6.8

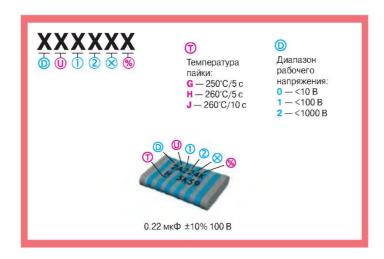
X - 7.5

K - 2.4

L - 2.7

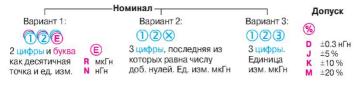
Допуск [%]:
 J — ±5,
 K — ±10,
 M — ±20

 -10^{7}



МАРКИРОВКА ИНДУКТИВНОСТЕЙ ДЛЯ ПОВЕРХНОСТНОГО МОНТАЖА





ТАБЛИЦЫ СООТВЕТСТВИЯ

Ниже приведены таблицы соответствия между параметрами и их обозначением с помощью цвета, символов и цифр. Для названий цвета используются следующие сокращения: чер — черный, кор — коричневый, кра — красный, т-кра — темно-красный, ора — оранжевый, жел — желтый, зел — зеленый, т-зел — темно-зеленый, гол — голубой, син — синий, фио — фиолетовый, сер — серый, бел — белый, зол — золотой, срб — серебрянный, роз — розовый, беж — бежевый, сал — салатовый, таб — табачный, бир — бирюзовый, эле — электрик.

⊕ ① ② ③ Маркировка номинального значения

Единица измерения: сопротивления — Ом, емкости — пФ, индуктивности — мкГн

Значение	0	1	2	3	4	5	6	7	8	9
Цветовая маркировка	чер	кор	кра	opa	жел	зел	ГОЛ	фио	cep	бел
Цифровая марк.	0	1	2	3	4	5	6	7	8	9

Маркировка множителя

Значение	0	0.01	0.1	1	10	10 ²	10 ³	10 ⁴	10 ⁵	10 ⁶	10 ⁷	10 ⁸	10 ⁹
Цветовая маркировка В		срб	30Л	чер	кор	кра	opa	жел	зел	гол	фио	cep	бел
Цифровая	R	7	8	9	1	2	3	4	5	6			
	С		9	0	1	2	3	4	5	6	7	8	

В Маркировка единицы измерения

Положение символа указывает на положение десятичной точки

			Con	ротивле	ния			Емкости	1	Индуктивности		
Знач	ение	Ом	кОм	МОм	ГОм	ТОм	пФ	нФ	мкФ	нГн	мкГн	
Сим-	межд.	R	K	М	G	T	R,P	n	m,µ	N	R	
вол	pyc.	E	K	M	Г	T	П	Н	100			

Маркировка допуска

Значе [%		±0.001	±0.002	±0.005	±0.01	±0.02	±0.05	±0.1	±0.25	±0.5	Ŧ	±2	±5	±10	±20	130	-10+30	-10+50	-10+100	-20 +50	-20 +80
Цве- товая	R						сер	фио	гол	зел	кор	кра	30Л	срб							
мар- киров- ка	C								opa	жел	кор	кра	30Л	срб	чер	сер				фио	cep
Сим- вол:	межд. рус.	Ε	L	R	Р	U	Α	В Ж*	C y*	D Д*	F P*	G Л	J И	K	M B	N Φ	QO	Т Э	Y Ю	S 5	Z

^{*} Для конденсаторов емкостью <10 пф допуск имеет размерность пикофарад. Для индуктивности используются допуски $\pm 5\%$, $\pm 10\%$ и $\pm 20\%$, символ D = ± 0.3 нГн

Маркировка температурного коэффициента сопротивлений

Значение	1	5	10	15	25	50	100
Цвет	cep	фио	гол	opa	жел	кра	кор
Символ (межд.)					Е	С	D

Маркировка ненормируемого температурного коэффициента емкости

Группа	H10	H20	H30	H50	H70	H90
Допуск в диапозоне –60+85°C	±10%	±20%	±30%	±50%	±70%	±90%
Цвет*	ора+чер	ора+кра	ора+зел	ора+гол	ора+фио	ора+бел
Символ (межд.)	В	Z	D	Х	E	F

^{*} Современная цветовая кодировка. Цветные полоски или точки. Второй цвет может быть представлен цветом корпуса.

Маркировка линейного температурного коэффициента емкости

Груп-	межд.	P100		NP0	N030	N080	N150	N220	N330	N470	N750	N1500	N2200
па	pyc.	П100	П33	МПО	M33	M75	M150	M220	M330	M470	M750	M1500	M2200
	KE n/°C]	100	33	0	-33	-75	-150	-220	-330	-470	-750	-1500	-2200
Разб	брос*	-49 +130		-75 +30	-80 +30	-80 +30	-105 +30	-120 +30	-180 +60	-210 +60	-330 +120	-670 250	8
Цве	ет**	кра+фио	cep	чер	кор	кра	opa	жел	зел	гол	фио	opa+opa	жел+ора
	ивол жд.)	A	N	С	Н	L	Р	R	S	Т	U	٧	К

^{*} Реальный разброс для импортных конденсаторов в диапазоне температур -55...+85°С.

® Маркировка нелинейного температурного коэффициента емкости

Обозначения групп приведены в соответствии со стандартом EIA, в скобках указан стандарт IEC. Маркировка дана в соответствии с EIA. Некоторые фирмы, например Panasonic, пользуются другой кодировкой.

				45	Доп	уск		
l		±7.5%	±10%	±15%	±22%	+2256%	+2282%	+1501500%
*.	-10+85°C	Z5F: B	Z5P: C		Z5S	Z5U (2E): E	Z5V: F ,	
диап	-30+85°C	Y5F	Y5P:	Y5R: R ,	Y5S: S,	Y5U: A	Y5V (2F)	
	-55+85°C	X5F	X5P		X5S	X5U:	X5V	
Temn	-55+125°C			X7R (2R)				
Pe	-55+150°C							SLO (GP):Nil,

^{*} В зависимости от технологий, которыми обладает фирма, диапазон может быть другим. Например, фирма Philips для группы Y5P нормирует –55...+125 °C.

О Маркировка рабочего напряжения емкостей

Значение [В]	2.5	3	4	6.3/7	10	16	20	25	35	50	63	100	250	400	630
Код (межд.)	0E,E		0G,G	0,1,0	1A,A	1C,C	1D,D	1E,V	1V,V	1H	1J	2A	2E	2G	2J

^{**} Современная цветовая кодировка в соответствии с EIA. Цветные полоски или точки. Второй цвет может быть представлен цветом корпуса.

РЯДЫ НОМИНАЛЬНЫХ ЗНАЧЕНИЙ ПО ЕІА

Допуски: E3 - 50%, E6 - 20%, E12 - 10%, E24 - 5%, E48 - 2%, E96 - 1%, E192 - < 0.5%

Не использ.	E3	100				220				470			
Редко исп.	E6	100		150		220		330		470		680	
	E12	100	120	150	180	220	270	330	390	470	560	680	820
	E24	100 110	120 130	150 160	180 200	220 240	270 300	330 360	390 430	470 510	560 620	680 750	820 910

E48	E96	E192															
100	100	100	147	147	147	215	215	215	316	316	316	464	464	464	681	681	681
		101			149			218			320			470			690
	102	102		150	150		221	221		324	324		475	475		698	698
		104			152			223			328			481			706
105	105	105	154	154	154	226	226	226	332	332	332	487	487	487	715	715	715
		106			156			229			336			493			723
	107	107		158	158		232	232		340	340		499	499		732	732
		109			160			234			344			505			741
110	110	110	162	162	162	237	237	237	348	348	348	511	511	511	750	750	750
		111			164			240			352			517			759
	113	113		165	165		243	243		357	357		523	523		768	768
		114			167			246			361			530			777
115	115	115	169	169	169	249	249	249	365	365	365	536	536	536	787	787	787
		117			172			252			370			542			796
	118	118		174	174		255	255		374	374		549	549		806	806
		120			176			258			379			556			816
121	121	121	178	178	178	261	261	261	383	383	383	562	562	562	825	825	825
		123			180			264			388			569			835
	124	124		182	182		267	267		392	392		576	576		845	845
		126			184			271			397			583			856
127	127	127	187	187	187	274	274	274	402	402	402	590	590	590	866	866	866
		129			189			277			407			597			876
	130	130		191	191		280	280		412	412		604	604		887	887
		132			193			284			417			612			898
133	133	133	196	196	196	287	287	287	422	422	422	619	619	619	909	909	909
		135			198			291			427			626			920
	137	137		200	200		294	294		432	432		634	634		931	931
		138			203			298			437			642			942
140	140	140	205	205	205	301	301	301	442	442	442	649	649	649	953	953	953
		142			208			305			448			657			965
	143	143		210	210		309	309		453	453		665	665		976	976
		145			213			312			459			673			988

МАРКИРОВКА ОТЕЧЕСТВЕННЫХ П/П ПРИБОРОВ В КОРПУСЕ КТ-26 (ТО-92)

Нет, не удалось нам догнать буржуев нигде, кроме как в области цветовой и кодовой маркировки райокомпонентов. Здесь мы не только догнали загнивающий Запад, но и перегнали его, как говорится, «навсегда». Никакому иностранцу никогда не удастся расшифровать таниственные и постоянно меняющиеся комбинации странных значков и таинственных точечек, коими маркируются отечественные полупроводниковые приборы. Что, в общем-то, хорошо: чего не понимают, того хотя бы опасаются, так что можно считать отечественную маркировку частью нашей оборонной инициативы, как говорится, «наш ответ на ультиматум Керзона». Но в своей страсти зашифровывать и засекречивать все и вся мы зашли слишком далеко, так как и собственное население уже не может понять, что же за загадочные приборы влаяны в наши неказистые платы.

Невозможно объять необъятное, поэтому из всей массы приборов мы постарались выбрать группу, которая наиболее часто маркируется всевозможными кодами. Понятно, что применение кодовой маркировки связано в первую очередь с размерами, а значит, и типом корпуса. Безусловным лидером по частоте применения кодовой маркировки является корпус типа КТ-26. Выпускавшийся ранее корпус КТП-4 представляет собой модификацию КТ-26 и, следовательно, тоже попадает под рассмотрение. В связи с вышеизложенным, упор, сделанный в данном издании на маркировку полупроводниковых приборов, выпускающихся в корпусе КТ-26, является закономерным и позволяет ответить на большинство вопросов, связанных с кодовой маркировкой.

Первый и самый неутешительный вывод, полученный в результате исследований: по маркировке полупроводниковых приборов, выпускающихся в корпусе КТ-26, часто НЕВОЗМОЖНО одновначно установить тип прибора. Можно долго рассуждать, почему так случилось и кто в этом виноват; мы же считаем, что сложившаяся ситуация является, результатом во-первых, нашего российского менталитета, то есть привычкой решать все проблемы административным путем, а воторых, сосбенностей протекания исторического процесса в нашей стране. Из последнего утверждения следует очень важный вывод: маркировка полупроводниковых приборов, выпускающихся в корпусе КТ-26, есть категория историческая. Это значит, в частности, что если производитель какото-нибудь транзистора в 1992 году маркировал его, допустим, красной точкой а в 1993 году перестал выпускать этот транзистор, то в 1994 году мог появиться другой (а иногда и тот же самый) производитель и замаркировать красной точкой совершенно другой прибор, считая, что данная конкуретная маркировка «свободна».

Вообще-то, служение полупроводниковой промышленности в советское время нуждам военнопромышленного комплекса не пошло ей на пользу. До сих пор принципы маркировки компонентов их изготовитель считает исключительно своей прерогативой и руководствуется в них даже не ГОС-Тами, а своими сиюминутными интересами, как-то: наличием или отсутствием необходимой краски, трудностями, связанными с изготовлением клейма, и т.п. Выполнение требований по маркировке, внесенных в ТУ, обходят обычно следующим образом: достаточно крупные партии приборов выпускаются «по нормали главного конструктора» или «по конкретному контракту», что позволяет маркировать эти партии так, как удобно изготовителю. Еще «хлеще» маркируются приборы, выпускаемые в странах СНГ для российского рынка. Самостийность, видимо, не позволяет маркировать по российским стандартам, а свои вырабатывать просто некогда, да и некому, надо быстрее клепать приборы, а то скоро эту «высокотехнологичную продукцию» никто брать не будет. Исключения в лучшую сторону достаточно редки и серьезного исследователя интересовать не могут.

История

Первым массовым транзистором с кодовой маркировкой был KT315 в миниатюрном пластмассовом корпусе KT-13. На нем в левом верхнем углу плоской стороны ставилась буква, обозначающая группу, ниже иногда указывалась дата изготовления. Через несколько лет в корпусе КТ-13 стали выпускать транзистор прямой проводимости — КТ361. Для отличия от КТ315 буква, обозначающая группу, ставилась посередине верхней части плоской сторо-



В 1974 году появился транзистор КТ375 в корпусе КТ-26 (тогда еще с круглыми выводами), который маркировался цифрами 375 и буквой, указывающей группу транзистора.

В 1976 году появляется целая группа транзисторов в корпусах КТП-4 и КТ-26, отмаркированных цветовым четырехточечным кодом, и транзистор КТ209 (корпус КТП-4), который маркировался буквой А в левом нижнем углу плоской стороны корпуса. В правом нижнем углу плоской стороны корпуса буквой указывалась группа прибора, выше — двумя цифрами год, а еще выше — двумя цифрами дата изготовления. Понять, что это за приборы, без расшифровки кода было уже невозможно, поэтому 1976 год можно считать началом эры цветовой и кодовой маркировки корпуса КТ-26 в СССР.



В 1979 году появляются транзисторы в корпусе КТ-26, маркированные символами. Сначала символы ставятся где попало, но к 1985 году они обретают постоянное место в левом верхнем углу плоской стороны корпуса. Примерно в это же время появляются транзисторы, маркируемые двумя цветовыми метками. С 1988 года набирает обороты сокращенная символьная маркировка.

Общие принципы маркировки

Корпус КТ-26 (ТО-92) изготавливается из пластмассы темного, чаще черного, цвета, поэтому все надписи наносятся белой или серебристой краской. Маркировка обычно наносится на среае боковой поверхности корпуса, реже — на цилиндрической части боковой поверхности корпуса, на торце корпуса цветовым кодом указывают группу прибора.

Встречаются приборы, торец корпуса которых целиком закрашен каким-либо цветом. Это, за немногими исключениями, внутризаводская маркировка, которая, как правило, не стандартизируется и не расшифровывается (обозначает иногда разбраковку по одному или нескольким параметрам: номер смены и т.п.). Уловить какие-нибудь закономерности здесь не удалось, да и не очень надо, так как для массового потребителя данный тип маркировки несет немного полезной информации.

На корпусе стараются указать тип прибора, группу, дату выпуска (год, месяц или номер смены). Наиболее важными представляются тип и группа прибора — на них мы и сосредоточим свое внимание; что касается даты изготовления, то часто она вообще не указывается. Когда же дата указывается, чаще всего это делается согласно ГОСТ 25486-82 (см. раздел Символьно-буквенная маркировка) или просто: двумя цифрами год, двумя (одной) месяц (например, 95 09 означает 1995 год, сентябрь-месяц). Встречается обратный порядок указания года и месяца (например, 3-74 означает март 1974 года) или обозначение только года изготовления двумя цифрами (например, 85 — 1985 год).

Типы маркировки полупроводниковых приборов

Для удобства все рассмотренные варианты маркировки полупроводниковых приборов, выпускающихся в корпусе КТ-26, были разбиты на шесть классов, которым были присвоены условные названия:



Цифро-буквенная маркировка

Цифро-буквенная маркировка может быть полной и сокращенной. Наносится на срез боковой поверхности корпуса, как правило, в две строки друг над другом, возможны как правый поворот надписи, так и левый, а также маркировка в одну строку. Относительно полный список сокращенного варианта цифро-буквенной маркировки приведен ниже в таблице (используемые условные обозначения расшифрованы в списке сокращений). Приборы, тип и группа которых промаркированы полностью, по понятным причинам в данном издании не рассматриваются.

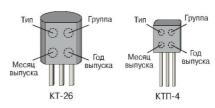


Тип	Фун- кция	1-2-3	Марки- ровка	Тип	Фун- кция	1-2-3	Марки- ровка	Тип	Фун- кция	1-2-3	Марки- ровка
KT969A1	n-p-n	E-C-B	1A	КП307Е1	n-FET	G-D-S	307E	KT349B	p-n-p	C-B-E	349B
KP1188EH5	reg+	I-C-O	8EH5	КП307Ж1	n-FET	G-D-S	307Ж	KT350A	p-n-p	C-B-E	350A
KP1188EH8	reg+	I-C-O	8EH8	KT313A1	p-n-p	C-B-E	313A1	KT351A	p-n-p	C-B-E	351A
KP1188EH9	reg+	I-C-O	8EH9	KT313A2	p-n-p	E-C-B	313A2	KT351E	p-n-p	C-B-E	3516
KP1188EH12	reg+	I-C-O	8EH12	KT313E1	p-n-p	C-B-E	31361	KT352A	p-n-p	C-B-E	352A
KT117AM	0	E-B1-B2	17A	KT313Б2	p-n-p	E-C-B	31352	KT352Б	p-n-p	C-B-E	3525
KT1176M	0	E-B1-B2	175	KT313B1	p-n-p	C-B-E	313B1	KT355AM	n-p-n	C-B-E	355A
KT117BM	0	E-B1-B2	17B	KT313B2	p-n-p	E-C-B	313B2	KT357B	p-n-p	C-B-E	357A
KT117FM	0	E-B1-B2	17Γ	KT313F1	p-n-p	C-B-E	313Г1	KT357A	p-n-p	C-B-E	357Б
KP1157EH1	reg+	C-0-I	57EH	KT313F2	p-n-p	E-C-B	313Г2	КТ357Б	p-n-p	C-B-E	357B
KP1168EH1	reg+	C-0-I	68EH1	KT3157A	p-n-p	C-E-B	3157A	KT361A2	p-n-p	E-C-B	361A2
KP142EH17A	reg+	0-C-I	69	KT315A1	n-p-n	E-C-B	315A1	KT361A3	p-n-p	E-C-B	361A3
KP142EH176	reg+	0-C-I	70	KT315Б1	n-p-n	E-C-B	315 E 1	KT361Б2	p-n-p	E-C-B	36162
KP142EH19	reg+	G-A-K	71	KT315B1	n-p-n	E-C-B	315B1	KT361B2	p-n-p	E-C-B	361B2
KT133A	0	B1-E-B2	133A	KT315F1	n-p-n	E-C-B	315Г1	КТ361Г2	p-n-p	E-C-B	361Г2
KT133E	0	B1-E-B2	133Б	КТ315Д1	n-p-n	E-C-B	315Д1	КТ361Г3	p-n-p	E-C-B	361Г3
КР1125КПЗА	btd	K-A1-A2	153A	KT315E1	n-p-n	E-C-B	315E1	КТ361Д2	p-n-p	E-C-B	361Д2
КР1125КПЗБ	btd	K-A1-A2	153E	KT315Ж1	n-p-n	E-C-B	315Ж1	КТ361Д3	p-n-p	E-C-B	361Д3
КР1125КПЗВ	btd	K-A1-A2	153B	КТ315И1	n-p-n	E-C-B	315И1	KT361E2	p-n-p	E-C-B	361E2
KT208A1	p-n-p	C-B-E	208A	KT315H1	n-p-n	E-C-B	315H1	КТ361Ж2	p-n-p	E-C-B	361Ж2
KT208E1	p-n-p	C-B-E	208Б	KT315P1	n-p-n	E-C-B	315P1	КТ361И2	p-n-p	E-C-B	361V/2
KT208B1	p-n-p	C-B-E	208B	KT316AM	n-p-n	C-B-E	316A(M)	KT361K2	p-n-p	E-C-B	361K2
KT209A	p-n-p	C-B-E	209A	КТ316БМ	n-p-n	C-B-E	316E(M)	КТ361Л2	p-n-p	E-C-B	361Л2
КТ209Б	p-n-p	C-B-E	209Б	KT316BM	n-p-n	C-B-E	316B(M)	KT361M2	p-n-p	E-C-B	361M2
KT209E1	p-n-p	C-B-E	209Б1	KT316FM	n-p-n	C-B-E	316F(M)	KT361H2	p-n-p	E-C-B	361H2
KT209B	p-n-p	C-B-E	209B	КТ316ДМ	n-p-n	C-B-E	316Д(М)	КТ361П2	p-n-p	E-C-B	361∏2
KT209B1	p-n-p	C-B-E	209B1	KT325AM	n-p-n	C-E-B	325A	KT363AM	p-n-p	C-B-E	363AM
KT209B2	p-n-p	C-B-E	209B2	КТ325БМ	n-p-n	C-E-B	325Б	КТ363БМ	p-n-p	C-B-E	363EM
KT209F	p-n-p	C-B-E	209Г	KT325BM	n-p-n	C-E-B	325B	КП364А	nFET	G-D-S	364A
КТ209Д	p-n-p	C-B-E	209Д	KT326AM	p-n-p	C-B-E	326AM	КП364Б	nFET	G-D-S	3645
KT209E	p-n-p	C-B-E	209E	КТ326БМ	p-n-p	C-B-E	326EM	КП364В	nFET	G-D-S	364B
КТ209Ж	p-n-p	C-B-E	209Ж	KT337A	p-n-p	C-B-E	337A	КП364Г	nFET	G-D-S	364Г
КТ209И	p-n-p	C-B-E	209И	КТ337Б	p-n-p	C-B-E	337Б	КП364Д	nFET	G-D-S	364Д
KT209K	p-n-p	C-B-E	209K	KT337B	p-n-p	C-B-E	337B	КП364Е	nFET	G-D-S	364E
КТ209Л	p-n-p	C-B-E	209Л	KT339AM	n-p-n	C-E-B	339A	КП364Ж	nFET	G-D-S	364Ж
KT209M	p-n-p	C-B-E	209M	KT342AM	n-p-n	C-B-E	342AM	КП364И	nFET	G-D-S	364И
KT219A	n-p-n	C-B-E	219A	KT3425M	n-p-n	C-B-E	3425M	KT368AM	n-p-n	C-B-E	368A/M
KT306AM	n-p-n	C-B-E	306A	KT342BM	n-p-n	C-B-E	342BM	КТ368БМ	n-p-n	C-B-E	368E/M
КТЗО6БМ	n-p-n	C-B-E	306Б	КТЗ42ГМ	n-p-n	C-B-E	342FM	KT368BM	n-p-n	C-B-E	368BM
KT306BM	n-p-n	C-B-E	306B	КТ342ДМ	n-p-n	C-B-E	342ДМ	KT373A	n-p-n	E-B-C	373A
KT306FM	n-p-n	C-B-E	306Г	KT345A	p-n-p	C-B-E	345A	КТ373Б	n-p-n	E-B-C	3736
КТЗОБДМ	n-p-n	C-B-E	306Д	KT3455	p-n-p	C-B-E	345B	KT373B	n-p-n	E-B-C	373B
КП307А1	n-FET	G-D-S	307A	KT345B	p-n-p	C-B-E	345B	КТ373Г	n-p-n	E-B-C	373F
КП307Б1	n-FET	G-D-S	307Б	KT349A	p-n-p	C-B-E	349A	KT375A	n-p-n	C-B-E	375A
КП307Г1	n-FET	G-D-S	307Г	KT3495	p-n-p	C-B-E	3496	КТ375Б	n-p-n	C-B-E	375Б

Тип	Фун- кция	1-2-3	Марки- ровка	Тип	Фун- кция		Марки- ровка	Тип	Фун- кция		Марки- ровка
KT399AM	n-p-n	C-B-E	399A	КТ686Г	p-n-p	1-2-3 C-B-E	686Г	КТ6110Д	n-p-n	1-2-3 E-B-C	6110Д
КТ399БМ	n-p-n	C-B-E	3995	КТ686Д	p-n-p	C-B-E	686Д	KT6111A	n-p-n	E-B-C	6111A
KT399BM	n-p-n	C-B-E	399B	KT686E	p-n-p	C-B-E	686E	KT6111B	n-p-n	E-B-C	6111E
КТ399ГМ	n-p-n	C-B-E	399Г	КТ686Ж	p-n-p	C-B-E	686Ж	KT6111B	n-p-n	E-B-C	6111B
КП501А	n-MOS	G-D-S	501A	KT698A	n-p-n	C-B-E	698A	КТ6111Г	n-p-n	E-B-C	6111Г
КП501Б	n-MOS	G-D-S	5015	КТ698Б	n-p-n	C-B-E	698Б	KT6112A	p-n-p	E-B-C	6112A
КП501В	n-MOS	G-D-S	501B	KT698B	n-p-n	C-B-E	698B	KT61125	p-n-p	E-B-C	6112E
КП502А	n-MOS	S-D-G	502A	КТ698Г	n-p-n	C-B-E	698F	KT6112B	p-n-p	E-B-C	6112B
KT502A	p-n-p	C-B-E	502A	КТ698Д	n-p-n	C-B-E	698Д	KT6113A	n-p-n	E-B-C	6113A
KT502Б	p-n-p	C-B-E	5025	KT698E	n-p-n	C-B-E	698E	KT6113E	n-p-n	E-B-C	6113E
KT502B	p-n-p	C-B-E	502B	КТ698Ж	n-p-n	C-B-E	698Ж	KT6113B	n-p-n	E-B-C	6113B
КТ502Г	p-n-p	C-B-E	502F	КТ698И	n-p-n	C-B-E	6981/	KT6113F	n-p-n	E-B-C	6113F
КТ502Д	p-n-p	C-B-E	502Д	KT698K	n-p-n	C-B-E	698K	КТ6113Д	n-p-n	E-B-C	6113Д
КТ502E КП503A	p-n-p n-MOS	C-B-E S-D-G	502E 503A	KT3102AM KT3102EM	n-p-n	C-B-E C-B-E	3102AM 31025M	KT6113E KT6114A	n-p-n	E-B-C E-B-C	6113E 6114A
KT503A	n-p-n	C-B-E	503A	KT3102BM	n-p-n n-p-n	C-B-E	3102BM	KT6114A	n-p-n n-p-n	E-B-C	6114B
KT503B	n-p-n	C-B-E	503E	KT3102EW	n-p-n	C-B-E	3102DM	KT6114B	n-p-n	E-B-C	6114B
KT503B	n-p-n	C-B-E	503B	КТ3102ДМ	n-p-n	C-B-E	3102ДМ	KT6114Γ	n-p-n	E-B-C	6114F
KT503F	n-p-n	C-B-E	503F	KT3102EM	n-p-n	C-B-E	3102EM	КТ6114Д	n-p-n	E-B-C	6114Д
КТ503Д	n-p-n	C-B-E	503Д	KT3102XM	n-p-n	C-B-E	3102XM	KT6114E	n-p-n	E-B-C	6114E
KT503E	n-p-n	C-B-E	503E	КТ3102ИМ	n-p-n	C-B-E	3102VM	KT6115A	p-n-p	E-B-C	6115A
КП504А	n-MOS	S-D-G	504A	KT3102KM	n-p-n	C-B-E	3102KM	KT6115B	p-n-p	E-B-C	6115B
КП504Б	n-MOS	S-D-G	5046	KT3107A	p-n-p	C-B-E	3107A	KT6115B	p-n-p	E-B-C	6115B
КП504В	n-MOS	S-D-G	504B	KT3107A1	p-n-p	B-C-E	3107A1	KT6115F	p-n-p	E-B-C	6115F
КП505А	n-MOS	S-D-G	505A	КТ3107Б	p-n-p	C-B-E	31075	КТ6115Д	p-n-p	E-B-C	6115Д
КП505Б	n-MOS	S-D-G	505E	KT3107Б1	p-n-p	B-C-E	310761	KT6115E	p-n-p	E-B-C	6115E
КП505В	n-MOS	S-D-G	505B	KT3107B	p-n-p	C-B-E	3107B	KT6116A	p-n-p	E-B-C	6116A
КП505Г	n-MOS	S-D-G	505F	KT3107B1	p-n-p	B-C-E	3107B1	KT6116B	p-n-p	E-B-C	6116E
КП523А	n-MOS	S-D-G	505F	KT3107F	p-n-p	C-B-E	3107	KT6117A	n-p-n	E-B-C	6117A
KC515F1	dz	-	515F1	KT3107F1	p-n-p	B-C-E	3107Г1	KT6117B	n-p-n	E-B-C	61175
KC520B1 KC531B1	dz dz		520B1 531B1	КТ3107Д КТ3107Д1	p-n-p	C-B-E B-C-E	3107Д 3107Д1	КТ6127A КТ6127Б	p-n-p	C-B-E C-B-E	6127A 6127 5
KT632A1	p-n-p	C-B-E	632A1	КТ3107Д1 КТ3107Е	p-n-p p-n-p	C-B-E	3107E	KT6127B	p-n-p p-n-p	C-B-E	6127B
KT632Б1	p-n-p	C-B-E	63251	KT3107E1	p-n-p	B-C-E	3107E1	KT6127F	p-n-p	C-B-E	6127F
KT632B1	p-n-p	C-B-E	632B1	КТЗ107Ж	p-n-p	C-B-E	3107Ж	КТ6127Д	p-n-p	C-B-E	6127Д
KT638A	n-p-n	C-B-E	638A	КТ3107Ж1	p-n-p	B-C-E	3107Ж1	KT6127E	p-n-p	C-B-E	6127E
КТ638Б	n-p-n	C-B-E	638E	КТ3107И	p-n-p	C-B-E	3107И	КТ6127Ж	p-n-p	C-B-E	6127Ж
KT645A	n-p-n	C-B-E	645A	КТ3107И1	p-n-p	B-C-E	3107И1	КТ6127И	p-n-p	C-B-E	6127И
KT645B	n-p-n	C-B-E	645B	KT3107K	p-n-p	C-B-E	3107K	KT6127K	p-n-p	C-B-E	6127K
KT660A	n-p-n	C-B-E	660A	KT3107K1	p-n-p	B-C-E	3107K1	KT6128A	n-p-n	E-B-C	6128A
КТ660Б	n-p-n	C-B-E	660E	КТ3107Л	p-n-p	C-B-E	3107Л	KT6128E	n-p-n	E-B-C	6128 5
KT668A	p-n-p	C-B-E	668A	КТ3107Л1	p-n-p	B-C-E	3107Л1	KT6128B	n-p-n	E-B-C	6128B
КТ668Б	p-n-p	C-B-E	6685	KT3117A1	n-p-n	C-B-E	3117	KT6128F	n-p-n	E-B-C	6128Г
KT668B	p-n-p	C-B-E	668B	KT3126A	p-n-p	C-B-E	3126A	КТ6128Д	n-p-n	E-B-C	6128Д
KT680A	n-p-n	C-B-E	680A 681A	KT31265	p-n-p	C-B-E	31265	KT6128E	n-p-n	E-B-C	6128E
KT681A KT684A	p-n-p	C-B-E B-C-E	684A	KT3128A1 KT3128Б1	p-n-p	C-B-E C-B-E	3128A1 3128Б1	KT6133A KT6133B	p-n-p	C-B-E	6133A 6133B
KT6845	p-n-p	B-C-E	684E	KT31266A	p-n-p n-p-n	C-B-E	3166A	KT6133B	p-n-p p-n-p	C-B-E	6133B
KT684B	p-n-p p-n-p	B-C-E	684B	KT3166E	n-p-n	C-B-E	3166E	KT6134A	n-p-n	C-B-E	6134A
KT684F	p-n-p	B-C-E	684F	KT3166B	n-p-n	C-B-E	3166B	KT6134B	n-p-n	C-B-E	6134E
KT685A	p-n-p	C-B-E	685A	КТ3166Г	n-p-n	C-B-E	3166	KT6134B	n-p-n	C-B-E	6134B
КТ685Б	p-n-p	C-B-E	685E	KT6109A	p-n-p	E-B-C	6109A	KT6135A	n-p-n	C-B-E	6135A
KT685B	p-n-p	C-B-E	685B	KT6109E	p-n-p	E-B-C	6109E	KT6135B	n-p-n	C-B-E	6135E
КТ685Г	p-n-p	C-B-E	685F	KT6109B	p-n-p	E-B-C	6109B	KT6135B	n-p-n	C-B-E	6135B
КТ685Д	p-n-p	C-B-E	685Д	KT6109F	p-n-p	E-B-C	6109F	KT6135F	n-p-n	C-B-E	6135F
KT685E	p-n-p	C-B-E	685E	КТ6109Д	p-n-p	E-B-C	6109Д	KT6136A	p-n-p	С-В-Е	6136A
КТ685Ж	p-n-p	C-B-E	685XK	KT6110A	n-p-n	E-B-C	6110A	KT6137A	n-p-n	C-B-E	6137A
KT686A	p-n-p	C-B-E	686A	KT61105	n-p-n	E-B-C	6110E	KP1210EH1	ref	K-K-A	EH1
КТ686Б	p-n-p	C-B-E	686E	KT6110B	n-p-n	E-B-C	6110B		-		
KT686B	p-n-p	C-B-E	686B	KT6110F	n-p-n	E-B-C	6110F				

Цветовая четырехточечная маркировка

Использовалась до 1986 года. Почти все приборы, отмаркированные четырьмя цветными точками на срезе боковой поверхности корпуса, выпускались как в корпусе КТ-26 (Рис. 18), так и в корпусе КТП-4 (Рис. 19). Точки наносятся цветной эмалью типа ЭП140. Кодирование группы, месяца и года выпуска производится строго согласно цветовым рядам, приведенным в таблицах ниже. Так-



же в последней таблице приведены все варианты данного класса маркировки (расшифровку колонки «Функция» см. в списке сокращений).

М Левая нижняя точка (месяц выпуска)

Месяц	Январь	Февраль	Март	Апрель	Май	Июнь	Июль	Август	Сентябрь	Октябрь	Ноябрь	Декабрь
Цвет	беж	CNH	О 3ел	KDa	Сал	Cep	KOD	opa	эле	О бел	Жел	ГОЛ

Правая нижняя точка (год выпуска)

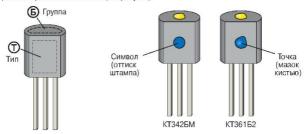
Год	1977	1978	1979	1980	1981	1982	1983	1984	1985	1986
Цвет	беж	Сал	opa	эле	бир	O 6en	кра	кор	О 3ел	ГОЛ

Варианты маркировки

						6	Цвет	право	ой вер	хней	точки	(букв	а груг	пы)	
(Ð	Тип	Функ- ция		A	Б	В	Г	Д	E	Ж	И	K	Л	M
				1-2-3	bo3	жел	CNH	беж	opa	бел	эле	can	зел	кра	cep
	ГОЛ	KT3107	p-n-p	C-B-E	Α	Б	В	г	Д		Е	ж	И	K	Л
	кор	KT326	p-n-p	C-B-E	AM	БМ									
	кра	KT337	p-n-p	C-B-E	Α	Б	В								
deci viceon echanica io ivai (iuii)	О бел	KT345	p-n-p	C-B-E	Α	Б	В								_
	СИН	KT349	p-n-p	С-В-Е	Α	Б	В				Œ	2	9 6		5)
	Сер	KT350	p-n-p	С-В-Е	Α						_		3 G		_
	жел	KT351	p-n-p	C-B-E	Α	Б					()	0 -		[D
•	О зел	KT352	p-n-p	C-B-E	Α	Б							С В Е Т337		
	D03	KT363	p-n-p	C-B-E	AM	БМ						Ма	рт, 19	979	

Символьно-цветовая маркировка

Основным признаком является наличие цветных геометрических символов на срезе боковой поверхности корпуса и отсутствие каких-либо букв/цифр. Тип прибора указывается на срезе боковой поверхности корпуса цветным геометрическим символом, группа — на торце корпуса цветным ночьками (см. рисунок). Различают два способа нанесения маркировки: в первом случае маркировка наносится с помощью накатки и занимает все поверхность от левого края до правого (первая таблица), а во втором случае символ наносится штампом (вторая таблица). Используемые в таблицах условные обозначения расшифрованы в списке сокращений. Следует различать символьную и двухточечную маркировку: кружок-символ наносится с помощью специального штампа и поэтому имеет четкую форму и «оттиснутый» вид, а точка наносится кистью и поэтому не имеет четкой формы, но заполняется краской гораздо более плотно (см. рисунок).



Символьно-цветовая маркировка накаткой

		20					(B)	Цвет	точк	инат	орце	(бук	за гру	ппы)		
C	D	Тип	Функ- ция	JIII 1-2-3	нет	кра	бел	зел	ГОЛ	ОО 2 бел	ОО 2 зел	●● 2 кра	ОО 2 гол	О ○ бел+ зел	О ● бел+ кра	ОО бел+ гол
		KT3102	n-p-n	C-B-E		AM	БМ	EM	ДМ	ВМ		ГМ		ИМ	ЖМ	KM
Ē		KT3107	p-n-p	C-B-E		ж	K	Б	Α	Л	Е	И	В	Γ	Д	
939		KT316	n-p-n	С-В-Е		AM	БМ	вм	ГМ	ДМ			(6).	en e	ž.
MCP		KT3144	n-p-n	C-B-E	Α								`		9	
KOBO	000	KT201	n-p-n	С-В-Е		AM	БМ	ВМ	ГМ	ДМ				58		
a 60		KT399	n-p-n	C-B-E		AM	БМ	ВМ	ГМ					12		
ТКан		KP1064KT1	btd	D-G-S		Α	Б	В	Г				0	7	Ш	
Накатка на боковом срезе (тип)		КЖ101	cld	I-C-0	A1								`	C	B E	
-	000	KC106	dz	C-B-E	A1									KT3	107 <i>A</i>	A

Маркировка отечественных п/п приборов в корпусе KT-26 (TO-92)

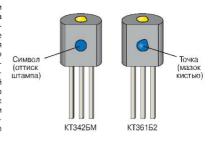
Символьно-цветовая маркировка геометрической фигурой

			Функ-				(B) ∟	цвет т	очки н	а тор	це (бу	ква гр	уппы)	le:	
Œ)	Тип	ция	1-2-3	нет	О бел	зел	кра	жел	CNIH	OО 2 бел	ОО 2 зел	О 2 кра	○ ○ 2 жел	2 син
	 бел	KT645	n-p-n	C-B-E	Α	Б									
	зел	KT645	n-p-n	C-B-E		И	Д	В	Г	E	М	Л	К	ж	
	О бел	KT645	n-p-n	C-B-E	Α	Б									
	3 ел	KT3126	p-n-p	C-B-E	Α		Б								
	CNH	KT361	p-n-p	E-C-B	A3*	A2	И2	Г3	Б2	Д2					
	D бел	KT6109	p-n-p	E-B-C		Α	Б	В	Г	Д					
	зел	KT6110	n-p-n	E-B-C		Α	Б	В	Γ	Д					
) бел	KT6114	n-p-n	E-B-C		Α	Б	В			Γ	Д	E		
Ē	— зел	KT6115	p-n-p	E-B-C		A	Б	В			Γ	Д	E		
нт) е	3 ел	KT6116	p-n-p	E-B-C	Α		Б								
Метка на боковом срезе (тип)	_ бел	KT6117	n-p-n	E-B-C	Α	Б									
KOBON	< бел	KT502	p-n-p	C-B-E		Α	Б	В	Г	Д	Е				
на 6с	Ф зел	KT503	n-p-n	C-B-E		Α	Б	В	Г	Д	Е				
Летка	3 ел	KT315	n-p-n	E-C-B		E1	B1	A1	Б1	Г1	P1	H1	Ж1	Д1	И1
_	[] бел	КП365	n-FET	G-S-D	Α	Б									
	зел	КП501	n-MOS	G-D-S	Α	Б	В								
	[][] бел	KT6111	n-p-n	E-B-C			В	Α	Б	Г					
	□ бел	KT3117	p-n-p	C-B-E	A1							'	5)
	3eH	КД130	d	A1-K-A2	AC										
	зел	КД130 КВ134	d var	K1-A-K2 K1-A-K2	AC1 A1										
	кра	KBC111	var	A1-K-A2		Α	В		Г	Б	Д-2	(ฮ์∏		
	CNH	KT660	n-p-n	C-B-E	Α								C KT	B E 503B	
	СИН	KT660	n-p-n	C-B-E	Б								KI	-00D	

^{*}АЗ,В2, ДЗ, Е2, Ж2, К2, Л2, М2, Н2, Г2, П2

Цветовая двухточечная маркировка

Отличается наличием цветной точки на срезе боковой поверхности корпуса (капля краски, наносимая кистью вручную), кодирующей тип прибора; на торце корпуса цветной точкой указывается группа. Точки маносятся цветной эмалью типа ЭП140 по ГОСТ 24709-81. Кодирование группы производится согласно цветовому раду, приведенному во второй строке таблицы с вариантами данного класса маркировки, хотя возможны как частичные нарушения этого ряда, так и полное пренебрежение ими. Расшифровку колонки «Функция» см. в списке сокращений.



Следует различать символьную и двухточечную маркировку: кружок-символ наносится с помощыю специального штампа и поэтому имеет четкую форму и «оттиснутый» вид, а точка наносится кистью и поэтому не имеет четкой формы, но заполняется краской гораздо более плотно (см. рисунок).

							6) Цв	ет точ	кина	а торі	це (б	уква	рупп	ы)		
(Ð	Тип	Фун- кция	1-2-3	нет	D03	А т-кра	Б	В т-зел	Г	Д	Е	Ж KOD	И О срб	K Opa	Л — таб	M Cep
	cep	KT209	p-n-p	C-B-E			Α	Б	В	Γ	Д	Е	ж	И	K	Л	М
	● т-зел	KT3102	n-p-n	C-B-E			AM	БМ	вм	ГМ	ДМ	ЕМ	ЖМ			ИМ	КМ
	таб	КП364	n-FET	G-D-S			Α	Б	В	Γ	Д	Е				И	
(пит)	кор	KT326	p-n-p	C-B-E		AM		БМ									
срезе	т-кра	KT203	p-n-p	C-B-E			AM	БМ	вм								
OBOM	кра	KT6112	p-n-p	E-B-C		2	Α	Б	В								
Цвет точки на боковом срезе (тип)	opa	KT313 KT638		C-B-E C-B-E			A1 A	Б1 Б	B1	Г1				 (6).			
TO4KM	жел	KT502	p-n-p	C-B-E			Α	Б	В	Γ	Д	E			0		
Цвет	ГОЛ	KT6111 KT339		E-B-C C-E-B	Α		Α	Б	В		Г			Ш	Ø	ı	
	СИН	KT342 KB131	n-p-n var	C-B-E A-K	A/A2		AM	БМ	ВМ	ГМ	ДМ						
	бел	KT503	n-p-n	C-B-E			А	Б	В	Г	Д	Е		(J =	
	Срб	KT632	p-n-p	C-B-E			A1	Б1	B1					KT3	3102	БМ	

Символьно-буквенная маркировка

Основным признаком этой маркировки является сочетание геометрических символов, букв и цифр. Срез боковой поверхности корпуса делится на четыре информационных поля. До 1991 года встречались различные порядки использования информационных полей (см. рисунок).

В настоящее время используется следующий порядок: верхнее левое поле обозначает тип прибора (один геометрический символ, буква или цифра), верхнее правое поле — группу (одна буква), нижнее левое поле — год выпуска, нижнее правое — месяц выпуска (дата согласно ГОСТ 25486-82).

Варианты маркировки приведены в таблице.



KT339AM

KT339AM

(м) Левый нижний символ (год выпуска)

Символ	U	٧	W	Х	Α	В	С	D	E	F	Н	1	K	L	М
Год	1986	1987	1988	1989	1990	1991	1992	1993	1994	1995	1996	1997	1998	1999	2000

Правый нижний символ (месяц выпуска)

	Символ	1	2	3	4	5	6	7	8	9	0	N	D
ſ	Месяц	Январь	Февраль	Март	Апрель	Май	Июнь	Июль	Август	Сентябрь	Октябрь	Ноябрь	Декабрь

Маркировка типономинала

T		Тип	Функ ция	1-2-3	T		Тип	Функ ция	1-2-3	0 6
Накатка на боковом срезе (тип)	1	KT632x1	p-n-p	C-B-E		Ц	KT6127x	p-n-p	C-B-E	A
	2	KT638 KT3102xM	n-p-n n-p-n	C-B-E		C	KT523x	p-n-p	C-B-E	E 5
	3	KT3102xM2	n-p-n	E-C-B		T	KT3166x	n-p-n	D-G-S	W III O
	4	KT3102xM2	n-p-n	E-C-B	Ē	T	KT313x1	p-n-p	I-C-O	CBE
	7	KT3107x2	p-n-p	B-C-E	e3e (1	•	KT503x	n-p-n	C-B-E	КТЗ102АМ май, 1994
	I	KT681A	p-n-p	C-B-E	МСР		KT502x	p-n-p	C-B-E	1 10 10 10 10 10 10 10 10 10 10 10 10 10
	IA	KP1157EHxx02A	reg+	O-C-I	KOBO		KT3102xM	n-p-n	C-B-E	① () ()
	A	КР1157EHxx01A КП364x	reg+ n-FET	C-I-O B-C-E	на бо	4	KT203xM	p-n-p	C-B-E	ПР
	Б	КП361х	n-FET	G-D-S	Накатка на боковом срезе (тип)	L	KT3157A	p-n-p	C-E-B	C_0
	В	КП307x1 КР1171СПxx	n-FET vd	G-D-S I-C-O		7	KT342xM	n-p-n	С-В-Е	Ø
	Г	KP1170EHxx KT680A	reg+ n-p-n	0-C-I 0-C-I		•	KT209x1	p-n-p	С-В-Е	CBE
	٦	KT680A3	n-p-n	C-B-E		▼	KT3107x2 KT326xM	p-n-p p-n-p	C-B-E C-B-E	КТ6127Б октябрь, 1992
	П	KT517x KT698x	n-p-n n-p-n			lack	KT339xM	n-p-n	C-E-B	

Нестандартизируемая маркировка

Включает приборы, маркировка которых не подпадает под вышеперечисленные классы. Многие из них приведены ниже.

КП403А



Одна или две цветные точки на корпусе (цвет не оговаривается)



KΠ402A

Две или три красных точки на торце корпуса



Перевернутый Т-образный знак в верхней части среза боковой стороны и буква группы под ним



Маленький кружок в центре среза боковой стороны и буква группы



Две белых точки на торце корпуса, расположенные перпендикулярно срезу



KT326

Розовая или желтая точка у коллектора на срезе боковой стороны



Одна или две белые или красные точки на торце корпуса



КР1125КП2

Белая точка на торце корпуса



Торец корпуса закрашен красным, синим или зеленым



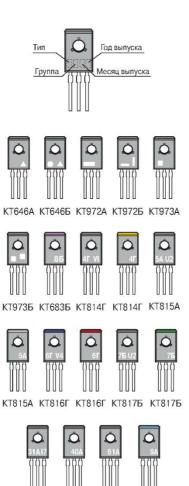
KH104A

Точка (обычно белая) у анода, длинный вывод не используется, анодом может быть любой из коротких выводов



Нет маркировки, длинный вывод не используется (неполярный прибор)

МАРКИРОВКА ОТЕЧЕСТВЕННЫХ П/П ПРИБОРОВ В КОРПУСЕ КТ-27 (TO-126)



KT8131A KT940 KT961A KT9115

МАРКИРОВКА П/П КОМПОНЕТОВ ДЛЯ ПОВЕРХНОСТНОГО МОНТАЖА

Назначение колонок в таблицах

Код — код, нанесенный на корпус. Сортировка по кодам задана с приоритетом цифр перед буквами, следовательно, код 618 расположен раньше, чем код 64S и 6A, а код А1 — после 9A. Бывают ситуации, когда совпадают код и тип корпуса, а приборы разные. Например, на корпусе типа SOT-323 нанесен код 6H. У фирмы «Philips» это л-р-л-транзистор типа BC8 18W, а у фирмы «Motorcla» это р-л-р-транзистор типа MUN5131T1 с совершенно другими параметрами;

Типономинал — типономинал (полное название прибора):

- Б сокращенное название фирмы-производителя. Например, SIEM фирма «Siemens», НР «Hewlett-Packard» и т.д. Для расшифровки необходимо воспользоваться таблицей «Список фирмпроизводителей», помещенной в конце книги:
- ф функциональное назначение прибора. Например, n-p-n-транзистор с указанной проводимостью, shd — диод Шоттки и т.д. Для расшиоровки необходимо воспользоваться таблицей «Список обозначений функции прибора», помещенной в конце книги;
- Особенности особенности или основные электрические характеристики прибора. Для расшифровки необходимо воспользоваться таблицей «Список сокращений и условных обозначений», помещенной в конце книги:
- Корпус название корпуса (ЕАЛ, JEDEC....); Ц/Цоколевка — цоколевка. Аббревиатуры выводов приводятся в порядке возрастания номеров выводов, начиная с первого. Нумерация выводов указана на корпусах в колонтитуле. Для расшифровки необходимо воспользоваться таблицей «Список сокращений и условных обозначений», помещенной в конце книги.

Код	Типономинал	Б	Φ	Особенности	Kopnyc SOD-91	Ц: 1•2 К•А
11D	BYD11D	PHIL	byg	$V_B < 200B$; $I_F < 0.5A$; $V_F (0.5A) < 0.91B$; $V_B > 225B$; $I_B < 1$ mKA; $C_D = 14$ n Φ ; $t_{BB} = 3$ mKC		
11 G	BYD11G	PHIL	byg	$V_R < 400B$; $I_F < 0.5A$, $V_F (0.5A) < 0.91B$; $V_R > 450B$; $I_R < 1$ m/A; $C_D = 14$ n Φ ; $t_{RR} = 3$ m/c	SOD-91	K•A
11J	BYD11J	PHIL	byg	$V_8 < 600B$; $I_F < 0.5A$, $V_F (0.5A) < 0.91B$; $V_8 > 650B$; $I_8 < 1$ mKA; $C_D = 14$ n Φ ; $t_{BB} = 3$ mKC	SOD-91	K•A
1 1K	BYD11K	PHIL	byg	V_R < 800 B; I_F < 0.5 A; V_F (0.5 A) < 0.91 B; V_R > 900 B; I_R < 1 m/A; C_D = 14 π Φ ; t_{RR} = 3 m/K c	SOD-91	K•A
11M	BYD11M	PHIL	byg	$V_R < 1000B$; $I_F < 0.5A$; $V_F (0.5A) < 0.91B$; $V_R > 1100B$; $I_R < 1$ mKA; $C_D = 14$ n Φ ; $I_{RR} = 3$ mKC	SOD-91	K•A
31D	BYD31D	PHIL	byg	$V_R < 200 B$; $I_F < 0.44 A$; $V_F (0.5 A) < 1.35 B$; $V_R > 300 B$; $C_D = 9 n\Phi$; $t_{RR} < 250 Hc$	SOD-91	K•A
31G	BYD31G	PHIL	byg	$V_R < 400 B$; $I_F < 0.44 A$; $V_F (0.5 A) < 1.35 B$; $V_R > 500 B$; $C_D = 9 \text{ m}\Phi$; $t_{RR} < 250 \text{ Hz}$	SOD-91	K•A
31J	BYD31J	PHIL	byg	$V_R < 600B$; $I_F < 0.44A$; $V_F (0.5A) < 1.35B$; $V_R > 700B$; $C_D = 9 \text{ m}\Phi$; $t_{RR} < 250 \text{ Hz}$	SOD-91	K•A
31K	BYD31K	PHIL	byg	$V_R < 800B$; $I_F < 0.44A$; $V_F (0.5A) < 1.35B$; $V_R > 900B$; $C_D = 8 \text{ m}\Phi$; $t_{RR} < 300 \text{ Hz}$	SOD-91	K•A
31M	BYD31M	PHIL	fid	$V_B < 1000B$; $I_F < 0.44A$; $V_F (0.5A) < 1.35B$; $V_B > 1100B$; $C_D = 8 \pi \Phi$; $t_{BB} < 300 Hc$	SOD-91	K•A
C10PH	BZV85-C10	PHIL	dz	$V_Z(I_{ZT} = 25 \text{ mA}) = 9.410.6 \text{ B}; Z_{ZT} < 8 \text{ Om}$	SOD-66	K•A
C11PH	BZV85-C11	PHIL	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 10.411.6 \text{ B; } Z_{ZT} < 10 \text{ Om}$	SOD-66	K•A
C12PH	BZV85-C12	PHIL	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 11.412.7 \text{ B; } Z_{ZT} < 10 \text{ Om}$	SOD-66	K•A
C13PH	BZV85-C13	PHIL	dz	$V_{z}(I_{zz} = 20 \text{ mA}) = 12.414.1 \text{ B}; Z_{zz} < 10 \text{ Om}$	SOD-66	K•A
C15PH	BZV85-C15	PHIL	dz	$V_Z(I_{ZT} = 15 \text{ mA}) = 13.815.6 \text{ B}; Z_{ZT} < 15 \text{ Om}$	SOD-66	K•A
C16PH	BZV85-C16	PHIL	dz	$V_Z(I_{ZT} = 15 \text{ mA}) = 15.317.1 \text{ B; } Z_{ZT} < 15 \text{ Om}$	SOD-66	K•A
C18PH	BZV85-C18	PHIL	dz	$V_Z(I_{ZT} = 15 \text{ mA}) = 16.819.1 \text{ B}; Z_{ZT} < 20 \text{ Om}$	SOD-66	K•A
C20PH	BZV85-C20	PHIL	dz	$V_z(I_{zT} = 10 \text{ mA}) = 18.821.2 \text{ B}; Z_{zT} < 24 \text{ Om}$	SOD-66	K•A
C22PH	BZV85-C22	PHIL	dz	$V_z(I_{zz} = 10 \text{ mA}) = 20.823.3 \text{ B}; Z_{zz} \le 25 \text{ Om}$	SOD-66	K+A
C24PH	BZV85-C24	PHIL	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 22.825.6 \text{ B}; Z_{ZT} < 30 \text{ Om}$	SOD-66	K•A
C27PH	BZV85-C27	PHIL	dz	$V_2(I_{21} = 8 \text{ mA}) = 25.128.9 \text{ B}; Z_{21} < 40 \text{ Om}$	SOD-66	K•A
C30PH	BZV85-C30	PHIL	dz	$V_7(I_{77} = 8 \text{ mA}) = 2832 \text{ B}; Z_{77} < 45 \text{ Om}$	SOD-66	K•A
СЗЗРН	BZV85-C33	PHIL	dz	$V_2(I_{27} = 8 \text{ mA}) = 3135 \text{ B}; Z_{27} < 45 \text{ Om}$	SOD-66	K•A
C36PH	BZV85-C36	PHIL	dz	$V_z(I_{zz} = 8 \text{ mA}) = 3438 \text{ B}; Z_{zz} < 50 \text{ Om}$	SOD-66	K•A
C39PH	BZV85-C39	PHIL	dz	$V_2(I_{21} = 6 \text{ mA}) = 3741 \text{ B; } Z_{21} < 60 \text{ Om}$	SOD-66	K•A
C3V6PH	BZV85-C3V6	PHIL	dz	$V_2(I_{2T}=60 \text{ mA})=3.43.8 \text{ B}; Z_{2T}<15 \text{ Om}$	SOD-66	K•A
C3V9PH	BZV85-C3V9	PHIL	dz	$V_2(I_{2T}=60 \text{ mA})=3.74.1 \text{ B; } Z_{2T}<15 \text{ Om}$	SOD-66	K•A
C43PH	BZV85-C43	PHIL	dz	$V_2(I_{27} = 6 \text{ mA}) = 4046 \text{ B}; Z_{27} < 75 \text{ Om}$	SOD-66	K•A
C47PH	BZV85-C47	PHIL	dz	$V_2(I_{27} = 4 \text{ mA}) = 4450 \text{ B}; Z_{27} < 100 \text{ Om}$	SOD-66	K•A
C4V3PH	BZV85-C4V3	PHIL	dz	$V_2(I_{2T} = 50 \text{ mA}) = 4.04.6 \text{ B}; Z_{2T} < 13 \text{ Om}$	SOD-66	K•A
C4V7PH	BZV85-C4V7	PHIL	dz	$V_2(I_{2T} = 45 \text{ mA}) = 4.45.0 \text{ B; } Z_{2T} < 13 \text{ Om}$	SOD-66	K•A
C51PH	BZV85-C51	PHIL	dz	$V_7(I_{27} = 4 \text{ mA}) = 4854 \text{ B}; Z_{77} < 125 \text{ Om}$	SOD-66	K•A
C56PH	BZV85-C56	PHIL	dz	$V_z(I_{z_T} = 4 \text{ mA}) = 5260 \text{ B}; Z_{z_T} < 150 \text{ Om}$	SOD-66	K•A
C5V1PH	BZV85-C5V1	PHIL	dz	$V_2(I_{2T} = 45 \text{ mA}) = 4.85.4 \text{ B}; Z_{2T} < 10 \text{ OM}$	SOD-66	K•A
C5V6PH	BZV85-C5V6	PHIL	dz	$V_2(I_{2T} = 45 \text{ mA}) = 5.26.0 \text{ B; } Z_{2T} < 70 \text{ m}$	SOD-66	K•A
C62PH	BZV85-C62	PHIL	dz	$V_7(I_{77} = 4 \text{ mA}) = 5866 \text{ B}; Z_{77} < 175 \text{ Om}$	SCD-66	K•A
C68PH	BZV85-C68	PHIL	dz	$V_{7}(I_{77} = 4 \text{ mA}) = 6472 \text{ B}; Z_{77} < 200 \text{ Om}$	SOD-66	K•A
C6V2PH	BZV85-C6V2	PHIL	dz	$V_z(I_{zT} = 35 \text{ mA}) = 5.86.6 \text{ B}; Z_{zT} < 4 \text{ Om}$	SOD-66	K•A
C6V8PH	BZV85-C6V8	PHIL	dz	$V_2(I_{2T}=35 \text{ mA})=6.47.2 \text{ B; } Z_{2T}<3.5 \text{ Om}$	SOD-66	K•A
C75PH	BZV85-C75	PHIL	dz	$V_2(I_{2T}=4 \text{ mA})=7080 \text{ B; } Z_{2T} \le 225 \text{ Om}$	SOD-66	K•A
C7V5PH		PHIL	dz	$V_2(I_{2T} = 35 \text{ mA}) = 7.07.9 \text{ B; } Z_{2T} \le 3.0 \text{ M}$	SOD-66	K•A
C8V2PH		PHIL	dz	$V_2(I_{2T} = 25 \text{ mA}) = 7.78.7 \text{ B; } Z_{2T} < 5.0 \text{ M}$	SOD-66	K•A
C9V1PH	BZV85-C9V1	PHIL	dz	V _z (I _{zT} = 25 mA) = 8.59 6 B; Z _{zT} < 5 Om	SOD-66	K•A
S11	BAS11	PHIL	dI	$V_B < 300 \text{ B}; I_E < 300 \text{ mA}; V_E (I_E = 300 \text{ mA}) < 1.0 \text{ B}; C_D = 20 \text{ n}\Phi; t_{BB} < 1 \text{mkc}$	SOD-91	K•A
S12	BAS12	PHIL	dl	V _R <400B; I _E <300 mA; V _E (I _E =300 mA)<1.0B; C _D =20 nΦ; t _{DR} <1mkc	SOD-91	K•A





SOD110, DO214, SMA/B/C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц:1•2
01C100PH	BZG01-C100	PHIL	dz	$V_Z(I_{ZT}=2.7 \text{ mA})=94106 \text{ B}; Z_{ZT}<350 \text{ Om}$	DO-214AC, SMA	K•A
01C10PH	BZG01-C10	PHIL	dz	$V_z (I_{ZT} = 25 \text{ mA}) = 9.410.6 \text{ B}; Z_{ZT} < 7 \text{ Om}$	DO-214AC, SMA	K∙A
01C110PH	BZG01-C110	PHIL	dz	V _z (I _{ZT} = 2.7 mA) = 104116B; Z _{ZT} < 450 Om	DO-214AC SMA	K∙A
01C11PH	BZG01-C11	PHIL	dz	$V_z(I_{ZT} = 20 \text{ mA}) = 10.411.6 \text{ B}; Z_{ZT} < 8 \text{ Om}$	DO-214AC, SMA	K•A
01C120PH	BZG01-C120	PHIL	dz	V _z (I _{ZT} = 2 mA) = 114127B; Z _{ZT} < 550 Om	DO-214AC, SMA	K•A
01C12PH	BZG01-C12	PHIL	dz	$V_Z(I_{ZT}=20 \text{ mA})=11.412.7 \text{ B}; Z_{ZT}<90 \text{ m}$	DO-214AC, SMA	K•A
01C130PH	BZG01-C130	PHIL	dz	V _Z (I _{ZT} = 2 mA) = 124141 B; Z _{ZT} < 700 Om	DO-214AC, SMA	K•A
01C13PH	BZG01-C13	PHIL	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 12.414.1 \text{ B}; Z_{ZT} < 100 \text{ m}$	DO-214AC, SMA	K∙A
01C150PH	BZG01-C150	PHIL	dz	$V_Z(I_{ZT} = 2 \text{ mA}) = 138156 \text{ B}; Z_{ZT} < 1000 \text{ Om}$	DO-214AC SMA	K•A
01C15PH	BZG01-C15	PHIL	dz	$V_Z(I_{ZT} = 15 \text{ mA}) = 13.815.6 \text{ B}; Z_{ZT} < 150 \text{ m}$	DO-214AC, SMA	K•A
01C160PH	BZG01-C160	PHIL	dz	V _Z (I _{ZT} = 1.5 mA) = 153171 B; Z _{ZT} < 1100 Om	DO-214AC, SMA	K•A
01C16PH	BZG01-C16	PHIL	dz	$V_z (I_{ZT} = 15 \text{ mA}) = 15.317.1 \text{ B}; Z_{ZT} < 150 \text{ m}$	DO-214AC, SMA	K•A
01C180PH	BZG01-C180	PHIL	dz	V _Z (I _{ZT} = 1.5 mA) = 168191 B; Z _{ZT} < 1200 Om	DO-214AC, SMA	K•A
01C18PH	BZG01-C18	PHIL	dz	$V_z (I_{ZT} = 15 \text{ mA}) = 16.819.1 \text{ B}; Z_{ZT} < 200 \text{ m}$	DO-214AC, SMA	K∙A
01C200PH	BZG01-C200	PHIL	dz	V _Z (I _{ZT} = 1.5 mA) = 188212 B; Z _{ZT} < 1500 Om	DO-214AC SMA	K•A
01C20PH	BZG01-C20	PHIL	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 18.821.2 \text{ B}; Z_{ZT} < 240 \text{ m}$	DO-214AC, SMA	K•A
01C220PH	BZG01-C220	PHIL	dz	$V_Z(I_{ZT} = 1 \text{ mA}) = 208233 \text{ B}; Z_{ZT} < 2250 \text{ Om}$	DO-214AC, SMA	K•A
01C22PH	BZG01-C22	PHIL	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 20.823.3 \text{ B}; Z_{ZT} < 250 \text{ m}$	DO-214AC, SMA	K•A
01C240PH	BZG01-C240	PHIL	dz	$V_Z(I_{ZT}=1 \text{ mA}) = 228256 \text{ B}; Z_{ZT} < 2550 \text{ Om}$	DO-214AC, SMA	K•A
01C24PH	BZG01-C24	PHIL	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 22.825.6 \text{ B}; Z_{ZT} < 250 \text{ m}$	DO-214AC SMA	K∙A
01C270PH	BZG01-C270	PHIL	dz	V _z (I _{ZT} = 1 mA) = 251289 B; Z _{ZT} < 3000 Om	DO-214AC SMA	K•A
01C27PH	BZG01-C27	PHIL	dz	V _Z (I _{ZT} = 8 mA) = 25.128.9 B; Z _{ZT} < 30 Om	DO-214AC, SMA	K•A
01C30PH	BZG01-C30	PHIL	dz	V _Z (I _{ZT} = 8 mA) = 2832 B; Z _{ZT} < 30 Om	DO-214AC, SMA	K•A
01C33PH	BZG01-C33	PHIL	dz	$V_Z(I_{ZT}=8 \text{ mA})=3135 \text{ B; } Z_{ZT}<350 \text{ m}$	DO-214AC, SMA	K∙A
01C36PH	BZG01-C36	PHIL	dz	$V_Z(I_{ZT} = 8 \text{ mA}) = 3438 \text{ B}; Z_{ZT} < 400 \text{ m}$	DO-214AC, SMA	K•A
01C39PH	BZG01-C39	PHIL	dz	$V_{Z}(I_{ZI}=6 \text{ mA})=3741 \text{ B; } Z_{ZI}<500 \text{ m}$	DO-214AC SMA	K•A
01C43PH	BZG01-C43	PHIL	dz	$V_Z(I_{ZI} = 6 \text{ mA}) = 4046 \text{ B}; Z_{ZI} < 500 \text{ m}$	DO-214AC SMA	K•A
01C47PH	BZG01-C47	PHIL	dz	$V_Z(I_{ZI} = 4 \text{ mA}) = 4450 \text{ B}; Z_{ZI} < 900 \text{ m}$	DO-214AC, SMA	K•A
01C51PH	BZG01-C51	PHIL	dz	$V_Z(I_{ZI} = 4 \text{ mA}) = 4854 \text{ B}; Z_{ZI} < 115 \text{ Om}$	DO-214AC, SMA	K∙A
01C56PH	BZG01-C56	PHIL	dz	$V_Z (I_{ZT} = 4 \text{ mA}) = 5260 \text{ B}; Z_{ZT} < 120 \text{ Om}$	DO-214AC, SMA	K∙A
01C62PH	BZG01-C62	PHIL	dz	$V_z (I_{ZT} = 4 \text{ mA}) = 5866 \text{ B}; Z_{ZT} < 125 \text{ Om}$	DO-214AC, SMA	K∙A
01C68PH	BZG01-C68	PHIL	dz	$V_z (I_{ZT} = 4 \text{ mA}) = 6472 \text{ B}; Z_{ZT} < 130 \text{ Om}$	DO-214AC, SMA	K•A
01C75PH	BZG01-C75	PHIL	dz	$V_Z(I_{ZT}=4 \text{ mA})=7079 \text{ B; } Z_{ZT} < 135 \text{ Om}$	DO-214AC, SMA	K•A
01C82PH	BZG01-C82	PHIL	dz	V _Z (I _{ZT} = 2.7 mA) = 7787B; Z _{ZT} < 200 Om	DO-214AC, SMA	K•A
01C91PH	BZG01-C91	PHIL	dz	$V_Z(I_{ZI} = 2.7 \text{ mA}) = 8596 \text{B}; Z_{ZI} < 250 \text{ Om}$	DO-214AC, SMA	K•A
03C100PH	BZG03-C100	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 94106 \text{ B}; Z_{ZT} < 200 \text{ Om}$	DO-214AC, SMA	K•A
03C10PH	BZG03-C10	PHIL	dz	$V_Z(I_{Z1} = 50 \text{ mA}) = 9.410.6 \text{ B}; Z_{Z1} < 4 \text{ Om}$	DO-214AC SMA	K•A
03C110PH	BZG03-C110	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 104116 \text{ B}; Z_{ZT} < 250 \text{ Om}$	DO-214AC SMA	K•A
03C11PH	BZG03-C11	PHIL	dz	$V_Z(I_{ZT} = 50 \text{ mA}) = 10.411.6 \text{ B}; Z_{ZT} < 70 \text{ m}$	DO-214AC SMA	K∙A
03C120PH	BZG03-C120	PHIL	dz	V _z (I _{ZT} = 5 mA) = 114127B; Z _{ZT} < 250 Om	DO-214AC, SMA	K•A
03C12PH	BZG03-C12	PHIL	dz	$V_Z(I_{ZT}=50 \text{ mA})=11.412.7 \text{ B}; Z_{ZT}<70 \text{ m}$	DO-214AC, SMA	K•A
03C130PH	BZG03-C130	PHIL	dz	V _z (I _{ZT} = 5 MA) = 124141 B; Z _{ZT} < 300 OM	DO-214AC, SMA	K•A
03C13PH	BZG03-C13	PHIL	dz	$V_z (I_{ZT} = 50 \text{ mA}) = 12.414.1 \text{ B}; Z_{ZT} < 100 \text{ m}$	DO-214AC SMA	K•A
03C150PH	BZG03-C150	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 138156B; Z _{ZT} < 300 Om	DO-214AC SMA	K•A
03C15PH	BZG03-C15	PHIL	dz	$V_Z (I_{ZT} = 50 \text{ mA}) = 13.815.6 \text{ B}; Z_{ZT} < 100 \text{ m}$	DO-214AC, SMA	K•A
03C160PH	BZG03-C160	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 153171 B; Z _{ZT} < 350 Om	DO-214AC, SMA	K•A
03C16PH	BZG03-C16	PHIL	dz	$V_z (I_{ZT} = 25 \text{ mA}) = 15.317.1 \text{ B}; Z_{ZT} < 150 \text{ m}$	DO-214AC, SMA	K•A
03C180PH	BZG03-C180	PHIL	dz	$V_Z(I_{ZT}=5 \text{ mA})=168191 \text{ B}; Z_{ZT}<400 \text{ Om}$	DO-214AC, SMA	K∙A
03C18PH	BZG03-C18	PHIL	dz	V _Z (I _{ZT} = 25 mA) = 16.819.1 B; Z _{ZT} < 150 m	DO-214AC SMA	K•A



Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2
03C200PH	BZG03-C200	PHIL	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 188212 \text{ B}; Z_{ZT} < 500 \text{ Om}$	DO-214AC, SMA	K•A
03C20PH	BZG03-C20	PHIL	dz	$V_z(I_{ZT} = 25 \text{ mA}) = 18.821.2 \text{ B}; Z_{ZT} < 15 \text{ Om}$	DO-214AC, SMA	K•A
03C220PH	BZG03-C220	PHIL	dz	$V_z(I_{ZT} = 2 \text{ mA}) = 208233 \text{ B}; Z_{ZT} < 750 \text{ Om}$	DO-214AC, SMA	K•A
03C22PH	BZG03-C22	PHIL	dz	$V_z(I_{zT} = 25 \text{ mA}) = 20.823.3 \text{ B}; Z_{zT} < 15 \text{ Om}$	DO-214AC, SMA	K•A
03C240PH	BZG03-C240	PHIL	dz	$V_2(I_{ZT} = 2 \text{ mA}) = 228256 \text{ B}; Z_{ZT} < 850 \text{ Om}$	DO-214AC, SMA	K•A
03C24PH	BZG03-C24	PHIL	dz	$V_z (I_{zz} = 25 \text{ mA}) = 22.825.6 \text{ B}; Z_{zz} < 15 \text{ Om}$	DO-214AC, SMA	K•A
03C270PH	BZG03-C270	PHIL	dz	$V_{z}(I_{zz} = 2 \text{ mA}) = 251289 \text{ B}; Z_{zz} < 1000 \text{ Om}$	DO-214AC, SMA	K•A
03C27PH	BZG03-C27	PHIL	dz	$V_2(I_{27} = 25 \text{ mA}) = 25.128.9 \text{ B}; Z_{27} < 15 \text{ Om}$	DO-214AC, SMA	K•A
03C30PH	BZG03-C30	PHIL	dz	$V_Z(I_{ZT} = 25 \text{ mA}) = 2832 \text{ B}; Z_{ZT} < 15 \text{ Om}$	DO-214AC, SMA	K•A
03C33PH	BZG03-C33	PHIL	dz	$V_z (I_{zt} = 25 \text{ mA}) = 3135 \text{ B}; Z_{zt} < 15 \text{ Om}$	DO-214AC, SMA	K•A
03C36PH	BZG03-C36	PHIL	dz	$V_z(I_{zT} = 10 \text{ mA}) = 3438 \text{ B}; Z_{zT} < 40 \text{ Om}$	DO-214AC, SMA	K•A
03C39PH	BZG03-C39	PHIL	dz	$V_z(I_{zt} = 10 \text{ mA}) = 3741 \text{ B}; Z_{zt} < 40 \text{ Om}$	DO-214AC, SMA	K•A
03C43PH	BZG03-C43	PHIL	dz	$V_z(I_{zt} = 10 \text{ mA}) = 4046 \text{ B}; Z_{zt} < 45 \text{ Om}$	DO-214AC, SMA	K•A
03C47PH	BZG03-C47	PHIL	dz	V _Z (I _{ZT} = 10 mA) = 4450B; Z _{ZT} < 45 Om	DO-214AC, SMA	K•A
03C51PH	BZG03-C51	PHIL	dz	V _Z (I _{ZT} = 10 mA) = 4854B; Z _{ZT} < 60 Om	DO-214AC, SMA	K•A
03C56PH	BZG03-C56	PHIL	dz	$V_2(I_{2T} = 10 \text{ mA}) = 5260 \text{ B; } Z_{2T} < 60 \text{ Om}$	DO-214AC, SMA	K•A
03C62PH	BZG03-C62	PHIL	dz	V _Z (I _{ZT} = 10 mA) = 5866B; Z _{ZT} < 80 Om	DO-214AC, SMA	K•A
03C68PH	BZG03-C68	PHIL	dz	V _Z (I _{ZT} = 10 mA) = 6472 B; Z _{ZT} < 80 Om	DO-214AC, SMA	K•A
03C75PH	BZG03-C75	PHIL	dz	V ₂ (I ₂₇ = 10 mA) = 7079B; Z ₂₇ < 100 Om	DO-214AC, SMA	K•A
03C82PH	BZG03-C82	PHIL	dz	V _z (I _{zT} = 10 mA) = 7787B; Z _{zT} < 100 Om	DO-214AC, SMA	K•A
03C91PH	BZG03-C91	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 8596 B; Z _{ZT} < 200 Om	DO-214AC, SMA	K•A
04100PH	BZG04-100	PHIL	VS	V _{BB} (I _T = 5 MA) = 114 B; V _{MM} = 167 B	DO-214AC, SMA	K•A
0410PH	BZG04-10	PHIL	vs	V _{BB} (I _T = 50 mA) = 11.4 B; V _{WM} = 17 B	DO-214AC, SMA	K•A
04110PH	BZG04-10	PHIL	vs vs	V _{RR} (I _T =5 MA) = 124 B; V _{WM} = 185 B	DO-214AC, SMA	K•A
0411PH	BZG04-11	PHIL	VS	V _{BR} (I _T = 50 MA) = 12.4 B; V _{WM} = 18.9 B	DO-214AC, SMA	K•A
04120PH	BZG04-120	PHIL	vs	V _{BB} (I _T = 5 mA) = 138 B; V _{WM} = 204 B	DO-214AC, SMA	K•A
04120FH	BZG04-120	PHIL	vs vs	V _{BB} (I _T = 50 MA) = 13.8 B; V _{WM} = 20.9 B	DO-214AC, SMA	K•A
04130PH	BZG04-130	PHIL	VS	V _{BB} (I _T = 5 mA) = 153 B; V _{WM} = 224 B	DO-214AC, SMA	K•A
04130FH	BZG04-130	PHIL	vs vs	V _{BB} (I _T = 25 MA) = 15.3 B; V _{WM} = 22.9 B	DO-214AC, SMA	K•A
04150PH	BZG04-150	PHIL	vs vs	V _{BR} (I _T = 5 MA) = 168 B; V _{WM} = 249 B	DO-214AC, SMA	K•A
04150FH	BZG04-150	PHIL	VS	V _{BB} (I _T = 25 MA) = 16.8 B; V _{WM} = 24.9 B	DO-214AC, SMA	K•A
04160PH	BZG04-160	PHIL	VS	V _{BB} (I _T = 5 mA) = 188 B; V _{WM} = 279 B	DO-214AC, SMA	K•A
0416PH	BZG04-160	PHIL	vs vs	V _{BB} (I _T = 25 MA) = 18.8 B; V _{WM} = 279 B	DO-214AC, SMA	K•A
04180PH	BZG04-180	PHIL	vs vs	V _{BR} (I _T = 2 MA) = 10.0 B; V _{WM} = 20.4 B V _{BR} (I _T = 2 MA) = 208 B; V _{WM} = 305 B	DO-214AC, SMA	K•A
0418PH	BZG04-180	PHIL	_	V _{BR} (I _T = 25 MA) = 20.8 B; V _{WM} = 31.0 B	DO-214AC, SMA	K•A
04200PH	BZG04-10	PHIL	VS	MANUAL CONTRACTOR AND	DO-214AC, SMA	K•A
04200PH	BZG04-200 BZG04-20	PHIL	vs	V _{BR} (I _T = 2 mA) = 228 B; V _{WM} = 336 B	DO-214AC, SMA	K•A
0420PH	BZG04-20 BZG04-220	PHIL	VS	V _{BR} (I _T = 25 MA) = 22.8 B; V _{VMM} = 33.8 B		K•A
04220PH 0422PH	BZG04-220 BZG04-22	PHIL	VS	V _{BR} (I _T = 2 mA) = 251 B; V _{WM} = 380 B	DO-214AC, SMA DO-214AC, SMA	K•A
0424PH		PHIL	VS	V _{BR} (I _T = 25 MA) = 25.1B; V _{VM} = 38.1B		11.
	BZG04-24		VS	V _{BR} (I _T = 25 mA) = 28 B; V _{WM} = 42.2B	DO-214AC, SMA	K•A
0427PH	BZG04-27	PHIL	VS	$V_{BR}(I_T = 25 \text{ mA}) = 31 \text{ B; } V_{WM} = 46.2 \text{ B}$	DO-214AC, SMA	K•A
0430PH	BZG04-30	PHIL	VS	$V_{BR}(I_T = 10 \text{ mA}) = 34 \text{ B}; V_{WM} = 50.1 \text{ B}$	DO-214AC, SMA	K•A
0433PH	BZG04-33	PHIL	VS	$V_{BR}(I_T = 10 \text{ mA}) = 37 \text{ B}; V_{WM} = 54.1 \text{ B}$	DO-214AC, SMA	K•A
0436PH	BZG04-36	PHIL	VS	$V_{BR}(I_T = 10 \text{ mA}) = 40 \text{ B}; V_{WM} = 60.7 \text{ B}$	DO-214AC, SMA	K•A
0439PH	BZG04-39	PHIL	VS	$V_{BR}(I_T = 10 \text{ mA}) = 44 \text{ B}; V_{WM} = 65.5 \text{ B}$	DO-214AC, SMA	K•A
0443PH	BZG04-43	PHIL	vs	$V_{BR}(I_T = 10 \text{ mA}) = 48 \text{ B}; V_{WM} = 70.8 \text{ B}$	DO-214AC, SMA	K•A
3447PH	BZG04-47	PHIL	VS	$V_{BR}(I_T = 10 \text{ mA}) = 52 \text{ B}; V_{WM} = 78.6 \text{ B}$	DO-214AC, SMA	K•A
0451PH	BZG04-51	PHIL	vs	V _{BR} (I _T = 10 mA) = 58 B; V _{WM} = 86.5 B	DO-214AC, SMA	K•A
0456PH	BZG04-56	PHIL	vs	$V_{BR}(I_T = 10 \text{ mA}) = 64 \text{ B}; V_{WM} = 94.4 \text{ B}$	DO-214AC, SMA	K•A
0462PH	BZG04-62	PHIL	νs	V _{BR} (I _T = 10 mA) = 70 B; V _{WM} = 103.5 B	DO-214AC, SMA	K•A
0468PH	BZG04-68	PHIL	vs	V _{BR} (I _T = 10 mA) = 77 B; V _{VM} = 114 B	DO-214AC, SMA	K•A
0475PH	BZG04-75	PHIL	vs	V _{BR} (I _T = 5 mA) = 85 B; V _{WM} = 126 B	DO-214AC, SMA	K∙A
0482PH	BZG04-82	PHIL	VS	$V_{BR}(I_T = 5 \text{ mA}) = 94 \text{ B}; V_{WM} = 139 \text{ B}$	DO-214AC, SMA	K•A





Код	Типономинал	6	Φ	Особенности	Kopnyc	Ц: 1•2
048V2PH	BZG04-8V2	PHIL	٧S	$V_{BR}(I_T = 50 \text{ mA}) = 9.4 \text{ B}; V_{WM} = 14.8 \text{ B}$	DO-214AC, SMA	K∙A
0491 PH	BZG04-91	PHIL	VS	V _{BR} (I _T = 5 мA) = 104 B; V _{WM} = 152 B	DO-214AC, SMA	K•A
049V1PH	BZG04-9V1	PHIL	VS	$V_{BR}(I_T = 50 \text{ mA}) = 10.4 \text{ B}; V_{WM} = 15.7 \text{ B}$	DO-214AC, SMA	K•A
10	SML4740	GS	dz	$V_Z (I_Z = 25.0 \text{ mA}) = 10 \text{ B}; Z_{ZT} = 7.0 \text{ Om}$	DO-214AC, SMA	K•A
10	U1ZB10	TOSH	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 9.011.0 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 300 \text{ m}$	DO-214AC, SMA	K•A
100	U1ZB100	TOSH	dz	$V_Z(I_{ZT}=3 \text{ mA})=90110 \text{ B}; Z_{ZT}(I_{ZT}=3 \text{ mA})<300 \text{ Om}$	DO-214AC, SMA	K•A
100A	P6SMB100AT3	ON	VS	V _{BR} (I _T =1 MA)=95105 B; V _{WM} =137B	DO-214AA, SMB	K•A
10A	1.5SMC10AT3	MOT	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 9.510.5 \text{ B}; V_{WM} = 8.55 \text{ B}; I_{pp} = 103 \text{ A}$	DO-214AB, SMC	K•A
10A	P6SMB10AT3	ON	VS.	V _{BR} (I _T = 1 mA) = 9.510.5 B; V _{WM} = 14.5 B	DO-214AA, SMB	K•A
11	SML4741	GS	dz	$V_{ZZ}(I_Z = 23.0 \text{ mA}) = 11 \text{ B}; Z_{ZT} = 8.0 \text{ Om}$	DO-214AC, SMA	K•A
11	U1ZB11	TOSH	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 9.912.1 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 300 \text{ m}$	DO-214AC, SMA	K•A
110	U1ZB110	TOSH	dz	$V_Z(I_{ZT}=3 \text{ mA})=99121 \text{ B}; Z_{ZT}(I_{ZT}=3 \text{ mA})<300 \text{ Om}$	DO-214AC, SMA	K•A
110A	P6SMB110AT3	ON	VS	V _{BR} (I _T = 1 mA) = 105116B; V _{WM} = 152B	DO-214AA, SMB	K•A
11A	1.5SMC11AT3	MOT	VS	V _{BR} (I _T = 1.0 mA) = 10.511.6B; V _{WM} = 9.4B; I _{PP} = 96A	DO-214AB, SMC	K•A
11A	P6SMB11AT3	ON	VS.	V _{BB} (I _T = 1 мA) = 10.511.6 B; V _{WM} = 15.6 B	DO-214AA, SMB	K•A
11C	P6SMB11CAT3	ON	VS	V _{BR} (I _T = 1 mA) = 10.511.6 B; V _{WM} = 15.6 B	DO-214AA, SMB	х∙х
12	SML4742	GS	dz	$V_2(I_2 = 21.0 \text{ mA}) = 12 \text{ B}; Z_{22} = 9.0 \text{ Om}$	DO-214AC, SMA	K•A
12	U1ZB12	TOSH	dz	$V_z(I_{zT} = 10 \text{ mA}) = 10.813.2 \text{ B}; Z_{zT}(I_{zT} = 10 \text{ mA}) < 300 \text{ m}$	DO-214AC, SMA	K•A
120A	P6SMB120AT3	ON	VS	V _{BB} (I _T = 1 mA) = 114126B; V _{MM} = 165B	DO-214AA, SMB	K•A
12A	1.5SMC12AT3	MOT	VS	V _{BR} (I _T = 1.0 mA) = 11.412.6B; V _{WM} = 10.2B; I _{PP} = 90A	DO-214AB, SMC	K•A
12A	P6SMB12AT3	ON	vs	V _{BB} (I _T =1 MA)=11.412.6 B; V _{WM} =16.7 B	DO-214AA, SMB	K•A
12C	P6SMB12CAT3	ON	vs	V _{BB} (I _T = 1 mA) = 11.412.6 B; V _{WM} = 16.7 B	DO-214AA, SMB	х∙х
13	SML4743	GS	dz	V _z (I _z = 19.0 mA) = 13 B; Z _{zz} = 10.0 Om	DO-214AC, SMA	K•A
13	U1ZB13	TOSH	dz	$V_z(I_{zz} = 10 \text{ mA}) = 11.714.3 \text{ B}; Z_{zz}(I_{zz} = 10 \text{ mA}) < 30 \text{ Om}$	DO-214AC SMA	K•A
130A	P6SMB130AT3	ON	VS	V _{BB} (I _T = 1 MA) = 124137B; V _{WM} = 179B	DO-214AA, SMB	K•A
13A	1.5SMC13AT3	MOT	VS	V _{BB} (I _T = 1.0 mA) = 12.413.7B; V _{WM} = 11.1B; I _{PP} = 82A	DO-214AB, SMC	K•A
13A	P6SMB13AT3	ON	VS	V _{BB} (I _T = 1 MA) = 12.413.7 B; V _{WM} = 18.2 B	DO-214AA, SMB	K•A
13C	P6SMB13CAT3	ON	VS	V _{BB} (I _T = 1 MA) = 12.413.7 B; V _{WM} = 18.2 B	DO-214AA, SMB	х∙х
15	SML4744	GS	dz	V _z (I _z = 17.0 mA) = 15 B; Z _{zT} = 14.00m	DO-214AC, SMA	K•A
15	U1ZB15	TOSH	dz	$V_7(I_{77} = 10 \text{ mA}) = 13.516.5 \text{ B}; Z_{77}(I_{77} = 10 \text{ mA}) < 30 \text{ Om}$	DO-214AC SMA	K•A
150	U1ZB150	TOSH	dz	$V_7(I_{7T} = 2 \text{ mA}) = 135165 \text{ B}; Z_{2T}(I_{2T} = 2 \text{ mA}) < 450 \text{ Om}$	DO-214AC, SMA	K•A
150A	P6SMB150AT3	ON	vs	V _{BB} (I _T = 1 MA) = 143158B; V _{MM} = 207B	DO-214AA, SMB	K•A
15A	1.5SMC15AT3	MOT	vs	V _{BB} (I _T = 1.0 mA) = 14.315.8B; V _{WM} = 12.8B; I _{PP} = 71A	DO-214AB, SMC	K•A
15A	P6SMB15AT3	ON	vs	V _{BB} (I _T = 1 MA) = 14.315.8 B; V _{WM} = 21.2 B	DO-214AA, SMB	K•A
15C	P6SMB15CAT3	ON	VS	V _{RR} (I _T = 1 MA) = 14.315.8 B; V _{WM} = 21.2 B	DO-214AA SMB	x•x
16	SML4745	GS	dz	V ₇ (I ₇ = 15.5 mA) = 16 B; Z ₇₇ = 16.0 Om	DO-214AC SMA	K•A
16	U1ZB16	TOSH	dz	$V_7(I_{77} = 10 \text{ mA}) = 14.417.6 \text{ B}; Z_{77}(I_{77} = 10 \text{ mA}) < 30 \text{ Om}$	DO-214AC, SMA	K•A
160A	P6SMB160AT3	ON	VS.	V _{BB} (I _T = 1 MA) = 152168 B; V _{WM} = 219 B	DO-214AA, SMB	K•A
16A	1.5SMC16AT3	MOT	VS	V _{BB} (I _T = 1.0 mA) = 15.216.8B; V _{WM} = 13.6B; I _{PP} =67A	DO-214AB, SMC	K•A
16A	P6SMB16AT3	ON	vs	V _{BB} (I _T = 1 mA) = 15.216.8 B; V _{WM} = 22.5 B	DO-214AA SMB	K•A
16C	P6SMB16CAT3	ON	vs	V _{BB} (I _T = 1 MA) = 15.216.8 B; V _{WM} = 22.5 B	DO-214AA, SMB	x•x
170A	P6SMB170AT3	ON	VS	V _{BR} (I _T = 1 mA) = 162179B; V _{WM} = 234B	DO-214AA, SMB	K•A
18	SML4746	GS	dz	V ₂ (I ₂ = 14.0 mA) = 18 B; Z ₇₁ = 20.0 Om	DO-214AC, SMA	K•A
18	U1ZB18	TOSH	dz	$V_2(I_{ZT} = 10 \text{ mA}) = 16.219.8 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 30 \text{ Om}$	DO-214AC, SMA	K•A
180	U1ZB180	TOSH	dz	$V_2(I_{ZT} = 1.5 \text{ mA}) = 162198 \text{ B; } Z_{ZT}(I_{ZT} = 1.5 \text{ mA}) < 500 \text{ Cm}$	DO-214AC SMA	K•A
180A	P6SMB180AT3	ON	VS.	V _{BB} (I _T =1 MA)=171189B; V _{MM} =246B	DO-214AA SMB	K•A
18A	1.5SMC18AT3	MOT	VS VS	V _{BR} (I _T = 1.0 MA) = 17.118.9B; V _{WM} = 15.3B; I _{PP} = 59.5A	DO-214AB, SMC	K•A
18A	P6SMB18AT3	ON	VS VS	V _{BB} (I _T =1.0MA)=17.118.9B; V _{WM} =15.3B, I _{PP} =39.3A V _{BB} (I _T =1 MA)=17.118.9B; V _{WM} =25.2B	DO-214AA, SMB	K•A
18C	P6SMB18CAT3	ON	vs vs	V _{BB} (I _T =1 MA)=17.118.9B; V _{WM} =25.2B	DO-214AA, SMB	X•X
1C	10BQ015	IR	shd	V _R <15B; VF<0.32B; I _F <1A	DO-214AA, SMB	K•A
1F	10BQ010	IR	shd	V _R <40B; VF<0.49B; I _F <1A	DO-214AA, SMB	K•A
1F	10MQ040N	IR	shd	V _R <40B; VF<0.51B; I _F <1.1A	DO-214AC, SMA	K•A
1J	10BQ100	IR	shd		DO-214AA, SMB	K•A
H	1080100	IIK	SNO	V _R < 100 B; VF < 0.62 B; I _F < 1 A	DO-214AA, SMB	K.A



Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2
1J	10MQ100N	IR	shd	V _R <100 B; VF<0.68 B; I _F < 2.1A	DO-214AC, SMA	K•A
1P	10BF10	IR	shd	$V_R < 100 \text{ B}; V_F < 0.95 \text{ B}; I_F < 1 \text{ A}; I_R < 100 \text{ mKA}; t_{RR} = 35 \text{ Hz}$	DO-214AA, SMB	K•A
1 P	10BF40	IR	shd	$V_R < 400 \text{ B}; V_F < 1.4 \text{ B}; I_F < 1 \text{ A}; I_R < 100 \text{ mKA}; t_{PR} = 50 \text{ HC}$	DO-214AA, SMB	K•A
1 S	10BF20	IR	shd	$V_R \le 200 \text{ B}; V_F \le 0.95 \text{ B}; I_F \le 1 \text{ A}; I_R \le 100 \text{ m/sA}; t_{RR} = 35 \text{ Hz}$	DO-214AA, SMB	K•A
1U	10BF60	IR	shd	V _R < 600 B; V _F < 1.7B; I _F < 1 A; I _R < 100 мкА; t _{ER} = 100 нс	DO-214AA, SMB	K∙A
1V	10BF80	IR	shd	$V_R < 800 \text{ B}; V_F < 1.7 \text{ B}; I_F < 1 \text{ A}; I_R < 100 \text{ mKA}; t_{PR} = 100 \text{ Hz}$	DO-214AA, SMB	K•A
1X	10BF100	IR	shd	$V_R \le 1000 \text{ B}; V_F \le 1.7 \text{ B}; I_F \le 1 \text{ A}; I_R \le 100 \text{ m/sA}; t_{RR} = 100 \text{ Hz}$	DO-214AA, SMB	K•A
20	SML4747	GS	dz	V _Z (Z = 12.5 mA) = 20 B; Z _{ZT} = 22.0 Om	DO-214AC, SMA	K∙A
20	U1ZB20	TOSH	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 18.022.0 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 30 \text{ Om}$	DO-214AC, SMA	K•A
200	U1ZB200	TOSH	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 180220 \text{ B}; Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 500 \text{ Om}$	DO-214AC, SMA	K•A
200A	P6SMB200AT3	ON	VS	V _{BR} (I _T = 1 mA) = 190210 B; V _{WM} = 274 B	DO-214AA, SMB	K•A
200Y	U1ZB200-Y	TOSH	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 190210 \text{ B}; Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 500 \text{ Om}$	DO-214AC, SMA	K∙A
200Z	U1ZB200-Z	TOSH	dz	$V_z(I_{ZT} = 0.5 \text{ mA}) = 200220 \text{ B}; Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 500 \text{ Om}$	DO-214AC, SMA	K•A
20A	1.5SMC20AT3	MOT	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 1921 \text{ B}; V_{WM} = 17.1 \text{ B}; I_{PP} = 54 \text{ A}$	DO-214AB, SMC	K•A
20A	P6SMB20AT3	ON	٧S	$V_{BR}(I_T = 1 \text{ mA}) = 1921 \text{ B}; V_{WM} = 27.7 \text{ B}$	DO-214AA, SMB	K•A
20C	P6SMB20CAT3	ON	vs	$V_{BR}(I_T = 1 \text{ mA}) = 1921 \text{ B}; V_{WM} = 27.7 \text{ B}$	DO-214AA, SMB	х∙х
22	SML4748	GS	dz	V ₂ (I ₂ =11.5 mA)=22B; Z _{ZT} =23.00m	DO-214AC, SMA	K∙A
22	U1ZB22	TOSH	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 19.824.2 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 30 \text{ Om}$	DO-214AC, SMA	K•A
220	U1ZB220	TOSH	dz	$V_z(I_{zz} = 0.5 \text{ mA}) = 198242 \text{ B}; Z_{zz}(I_{zz} = 0.5 \text{ mA}) < 5000 \text{ Om}$	DO-214AC, SMA	K•A
220Y	U1ZB220-Y	TOSH	dz	$V_z(I_{zz} = 0.5 \text{ mA}) = 210230 \text{ B}; Z_{zz}(I_{zz} = 0.5 \text{ mA}) < 5000 \text{ Om}$	DO-214AC, SMA	K•A
220Z	U1ZB220-Z	TOSH	dz	$V_z(I_{ZT} = 0.5 \text{ mA}) = 220240 \text{ B}; Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 5000 \text{ Om}$	DO-214AC, SMA	K•A
22A	1.5SMC22AT3	MOT	vs	$V_{BB}(I_T = 1.0 \text{ mA}) = 20.923.1 \text{ B}; V_{WM} = 18.8 \text{ B}; I_{pp} = 49 \text{ A}$	DO-214AB, SMC	K•A
22A	P6SMB22AT3	ON	vs	V _{BB} (I _T = 1 mA) = 20.923.1B; V _{MM} = 30.6B	DO-214AA, SMB	K•A
22C	P6SMB22CAT3	ON	vs	V _{BB} (I _T = 1 mA) = 20.923.1B; V _{MM} = 30.6B	DO-214AA, SMB	х∙х
24	SML4749	GS	dz	V ₂ (I ₂ =10.5 mA)=24B; Z ₂₇ =25.00m	DO-214AC, SMA	K•A
24	U1ZB24	TOSH		$V_z(I_{zT} = 10 \text{ mA}) = 21.626.4 \text{ B}; Z_{zT}(I_{zT} = 10 \text{ mA}) < 30 \text{ Om}$	DO-214AC, SMA	K•A
240	U1ZB240	TOSH	dz	$V_z(I_{ZT} = 0.5 \text{ mA}) = 216264 \text{ B}; Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 5000 \text{ Om}$	DO-214AC, SMA	K•A
240Y	U1ZB240-Y	TOSH	dz	$V_z(I_{ZT} = 0.5 \text{ mA}) = 230250 \text{ B}; Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 5000 \text{ Om}$	DO-214AC, SMA	K•A
240Z	U1ZB240-Z	TOSH		$V_z(I_{ZT} = 0.5 \text{ mA}) = 240260 \text{ B}; Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 5000 \text{ Om}$	DO-214AC, SMA	K•A
24A	1.5SMC24AT3	MOT	vs	V _{BB} (I _T = 1.0 mA) = 22.825.2B; V _{WM} = 20.5B; I _{PP} = 45 A	DO-214AB, SMC	K•A
24A	P6SMB24AT3	ON	vs	V _{BR} (I _T = 1 mA) = 22.825.2B; V _{MM} = 33.2B	DO-214AA, SMB	K•A
24C	P6SMB24CAT3	ON	vs	V _{BR} (I _T = 1 mA) = 22.825.2B; V _{MM} = 33.2B	DO-214AA, SMB	х∙х
27	SML4750	GS	dz	$V_Z(I_Z = 9.5 \text{ mA}) = 27 \text{ B}; Z_{ZT} = 35.0 \text{ Om}$	DO-214AC, SMA	K•A
27	U1ZB27	TOSH		V ₂ (I _{2T} = 10 mA) = 24.329.7 B; Z _{2T} (I _{2T} = 10 mA) < 30 Om	DO-214AC, SMA	K•A
270	U1ZB270	TOSH		$V_2(I_{77} = 0.5 \text{ mA}) = 243297 \text{ B}; Z_{27}(I_{77} = 0.5 \text{ mA}) < 5000 \text{ Om}$	DO-214AC, SMA	K•A
270X	U1ZB270-X	TOSH		V ₂ (I _{2T} = 0.5 mA) = 250270 B; Z _{2T} (I _{2T} = 0.5 mA) < 5000 Om	DO-214AC, SMA	K•A
270Y	U1ZB270-Y	TOSH		V ₂ (I _{2T} = 0.5 mA) = 260280 B; Z _{2T} (I _{2T} = 0.5 mA) < 5000 Om	DO-214AC, SMA	K•A
2707	U1ZB270-Z	TOSH		V _z (I _{zT} = 0.5 mA) = 270290 B; Z _{zT} (I _{zT} = 0.5 mA) < 5000 Om	DO-214AC, SMA	K•A
27A	1.5SMC27AT3	MOT	vs	V _{BR} (I _T = 1.0 mA) = 25.728.4B; V _{MM} = 23.1B; I _{pp} = 40 A	DO-214AB, SMC	K•A
27A	P6SMB27AT3	ON	vs	V _{BB} (I _T = 1 MA) = 25.728.4 B; V _{MM} = 37.5 B	DO-214AA, SMB	K•A
27C	P6SMB27CAT3	ON	vs	V _{BR} (I _T = 1 mA) = 25.728.4B; V _{MM} = 37.5B	DO-214AA, SMB	x•x
30	SML4751	GS	dz	V ₂ (I ₂ = 8.5 mA) = 30 B; Z _{2T} = 40.0 Om	DO-214AC, SMA	K•A
30	U1ZB30	TOSH		$V_7(I_{77} = 10 \text{ mA}) = 27.033.0 \text{ B; } Z_{77}(I_{77} = 10 \text{ mA}) < 30 \text{ Om}$	DO-214AC, SMA	K•A
300	U1ZB300	TOSH	100,000	$V_2(I_{ZT} = 0.5 \text{ mA}) = 270330 \text{ B; } Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 5000 \text{ Om}$	DO-214AC, SMA	K•A
300X	U1ZB300-X	TOSH		$V_2(I_{ZT} = 0.5 \text{ mA}) = 280300 \text{ B; } Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 5000 \text{ Om}$	DO-214AC, SMA	K•A
300X	U1ZB300-X	TOSH		$V_z(I_{ZT} = 0.5 \text{ mA}) = 290310 \text{ B}; Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 5000 \text{ OM}$	DO-214AC, SMA	K•A
300Z	U1ZB300-7	TOSH		$V_z(I_{ZT} = 0.5 \text{ mA}) = 300320 \text{ B; } Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 5000 \text{ OM}$	DO-214AC, SMA	K•A
30A	1.5SMC30AT3	MOT	VS.	V _{BB} (I _T = 1.0 MA) = 28.531.5B; V _{WM} = 25.6B; I _{PP} = 36A	DO-214AB, SMC	K•A
30A	P6SMB30AT3	ON	vs vs	V _{BR} (I _T = 1 mA) = 28.531.5B; V _{MM} = 21.4B	DO-214AA, SMB	K•A
30C	P6SMB30CAT3	ON	vs vs	V _{BR} (I _T = 1 mA) = 28.531.5B; V _{MM} = 41.4B	DO-214AA, SMB	X•X
33	SML4752	GS	dz	$V_2(I_2 = 7.5 \text{ mA}) = 33 \text{ B; } Z_{ZT} = 45.0 \text{ Om}$	DO-214AC, SMA	K•A
33	U1ZB33	TOSH		$V_Z(I_Z = 7.5 \text{ MA}) = 35 \text{ B}, Z_{ZT} = 45.0 \text{ OM}$ $V_Z(I_{ZT} = 10 \text{ MA}) = 29.736.3 \text{ B}, Z_{ZT}(I_{ZT} = 10 \text{ MA}) < 30 \text{ OM}$	DO-214AC, SMA	K•A
330	U1ZB330				DO-214AC, SMA	K•A
ooV .	U 14D00U	TOSH	UZ	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 297363 \text{ B}; Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 5000 \text{ Om}$	DU-214AU, SMA	N-A





Код	Типономинал	Б	Ф	Особенности	Kopnyc	Ц: 1•2
330X	U1ZB330-X	TOSH	dz	$V_z(I_{ZT} = 0.5 \text{ mA}) = 310330 \text{ B}; Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 5000 \text{ Cm}$	DO-214AC, SMA	K•A
330Y	U1ZB330-Y	TOSH	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 320340 \text{ B}; Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 5000 \text{ Om}$	DO-214AC, SMA	K•A
330Z	U1ZB330-Z	TOSH	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 330350 \text{ B}; Z_{ZT}(I_{ZT} = 0.5 \text{ mA}) < 5000 \text{ Om}$	DO-214AC, SMA	K•A
33A	1.5SMC33AT3	MOT	VS	V _{BR} (I _T = 1.0 mA) = 31.434.7B; V _{WM} = 28.2B; I _{PP} = 33A	DO-214AB, SMC	K•A
33A	P6SMB33AT3	ON	VS	$V_{BR}(I_T = 1 \text{ mA}) = 31.434.7 \text{ B}; V_{WM} = 45.7 \text{ B}$	DO-214AA, SMB	K•A
33C	P6SMB33CAT3	ON	VS	V _{BR} (I _T =1 MA)=31.434.7B; V _{WM} =45.7B	DO-214AA, SMB	х∙х
36	SML4753	GS	dz	V _Z (I _Z =7.0 mA) = 36 B; Z _{ZT} = 50.0 Om	DO-214AC, SMA	K•A
36	U1ZB36	TOSH	dz	$V_Z(I_{ZT} = 9 \text{ mA}) = 32.439.6 \text{ B}; Z_{ZT}(I_{ZT} = 9 \text{ mA}) < 30 \text{ Om}$	DO-214AC, SMA	K•A
36A	1.5SMC36AT3	MOT	VS.	V _{BR} (I _T = 1.0 mA) = 34.237.8B; V _{WM} = 30.8B; I _{PP} = 30A	DO-214AB, SMC	K•A
36A	P6SMB36AT3	ON	vs	V _{BR} (I _T = 1 mA) = 34.237.8 B; V _{WM} = 49.9 B	DO-214AA, SMB	K∙A
36C	P6SMB36CAT3	ON	VS	V _{BR} (I _T = 1 mA) = 34.237.8 B; V _{WM} = 49.9 B	DO-214AA, SMB	х∙х
39	SML4754	GS	dz	V _Z (I _Z =6.5 mA) = 39 B; Z _{ZT} = 60.0 Om	DO-214AC, SMA	K∙A
390	U1ZB390	TOSH	dz	V _Z (I _{ZT} = 0.5 mA) = 351429 B; Z _{ZT} (I _{ZT} = 0.5 mA) < 10000 Om	DO-214AC, SMA	K•A
39A	1.5SMC39AT3	MOT	VS	V _{BR} (I _T = 1.0 mA) = 37.141B; V _{WM} = 33.3B; I _{PP} = 28 A	DO-214AB, SMC	K∙A
39A	P6SMB39AT3	ON	VS	V _{BB} (I _T = 1 mA) = 37.141.0 B; V _{WM} = 53.9 B	DO-214AA, SMB	K∙A
39C	P6SMB39CAT3	ON	VS	V _{BR} (I _T = 1 mA) = 37.141.0 B; V _{WM} = 53.9 B	DO-214AA, SMB	χ●χ
3C	30BQ015	IR	shd	V _B = 15B; V _E < 0.3B; I _E = 3A	DO-214AB, SMC	K∙A
3F	15MQ40N	IR	shd	V _B <40B; VF<0.43B; I _F <3A	DO-214AC, SMA	K∙A
3F	30BQ040	IR	shd	V _B = 40B; V _E < 0.43B; I _E = 3A	DO-214AB_SMC	K∙A
3H	30BQ060	IR	shd	V _B = 60B; V _E < 0.52B; I _E = 3A	DO-214AB, SMC	K•A
3J	30BQ100	IR	shd	V _B = 100 B; V _F < 0.62 B; I _F = 3 A	DO-214AB, SMC	K•A
43	SML4755	GS	dz	$V_z(I_z = 6.0 \text{ mA}) = 43 \text{ B}; Z_{zz} = 70.0 \text{ Om}$	DO-214AC, SMA	K•A
43	U1ZB43	TOSH	dz	$V_z(I_{ZT} = 7 \text{ mA}) = 38.747.3 \text{ B}; Z_{ZT}(I_{ZT} = 7 \text{ mA}) < 40 \text{ Om}$	DO-214AC, SMA	K•A
43A	1.5SMC43AT3	MOT	VS	V _{BB} (I _T = 1.0 MA) = 40.945.2B; V _{WM} = 36.8B; I _{PP} = 25.3A	DO-214AB_SMC	K∙A
43A	P6SMB43AT3	ON	vs	V _{RR} (I _T = 1 mA) = 40.945.2 B; V _{MM} = 59.3 B	DO-214AA, SMB	K•A
43C	P6SMB43CAT3	ON	VS	V _{BB} (I _T = 1 mA) = 40.945.2 B; V _{WM} = 59.3 B	DO-214AA, SMB	х∙х
47	SML4756	GS	dz	V ₂ (I ₂ =5.5 mA) = 47 B; Z ₂₁ = 80.0 Om	DO-214AC, SMA	K•A
47	U1ZB47	TOSH	dz	$V_2(I_{ZT}=6 \text{ mA})=42.351.7 \text{ B}; Z_{ZT}(I_{ZT}=6 \text{ mA})<65 \text{ Om}$	DO-214AC, SMA	K•A
47A	1.5SMC47AT3	MOT	VS	V _{BB} (I _T = 1.0 MA) = 44.749.4B; V _{MM} = 40.2B; I _{PP} = 23.2A	DO-214AB, SMC	K•A
47A	P6SMB47AT3	ON	vs	V _{BB} (I _T = 1 MA) = 44.749.4 B; V _{MM} = 64.8 B	DO-214AA, SMB	K•A
47C	P6SMB47CAT3	ON	vs	V _{BB} (I _T = 1 MA) = 44.749.4 B; V _{MM} = 64.8 B	DO-214AA SMB	x•x
51	SML4757	GS	dz	V ₂ (I ₂ = 5.0 mA) = 51 B ₁ Z ₂₁ = 95.0 Om	DO-214AC, SMA	K•A
51	U1ZB51	TOSH	dz	V _Z (I _{ZT} = 6 mA) = 45.956.1 B; Z _{ZT} (I _{ZT} = 6 mA) < 65 Om	DO-214AC, SMA	K•A
51A	1.5SMC51AT3	MOT	VS	V _{BB} (I _T = 1.0 mA) = 48.553.6B; V _{MM} = 43.6B; I _{PP} = 21.4A	DO-214AB, SMC	K•A
51A	P6SMB51AT3	ON	vs	V _{BB} (I _T = 1 mA) = 48.553.6 B; V _{MM} = 70.1 B	DO-214AA SMB	K•A
51C	P6SMB51CAT3	ON	VS	V _{RR} (I _T = 1 MA) = 48.553.6 B; V _{MM} = 70.1 B	DO-214AA, SMB	х•х
56	SML4758	GS	dz	V ₇ (Z = 4.5 mA) = 56 B; Z _{7T} = 110.0 Om	DO-214AC, SMA	K•A
56A	1.5SMC56AT3	MOT	VS.	V _{BB} (I _T = 1.0 mA) = 53.258.8B; V _{MM} = 47.8B; I _{PP} = 19.5A	DO-214AB, SMC	K•A
56A	P6SMB56AT3	ON	vs	V _{BB} (I _T = 1 mA) = 53.258.8 B; V _{MM} = 77 B	DO-214AA, SMB	K•A
56C	P6SMB56CAT3	ON	vs	V _{BB} (I _T = 1 mA) = 53.258.8 B; V _{WM} = 77 B	DO-214AA SMB	x•x
6.8	U1ZB6.8	TOSH	dz	V _Z (I _{ZT} = 10 mA) = 6.27.4 B; Z _{ZT} (I _{ZT} = 10 mA) < 60 Om	DO-214AC, SMA	K•A
62	SML4759	GS	dz	V _Z (I _Z =4.0 mA)=62 B; Z _{ZT} =125.0 Om	DO-214AC, SMA	K•A
62A	1.5SMC62AT3	MOT	VS	V _{RB} (I _T = 1.0 mA) = 58.965.1B; V _{MM} = 53 B; I _{PP} = 17.7 A	DO-214AB, SMC	K•A
62A	P6SMB62AT3	ON	VS	V _{BB} (I _T =1 mA)=58.965.1 B; V _{WM} =85 B	DO-214AA SMB	K•A
62C	P6SMB62CAT3	ON	VS	V _{BB} (I _T =1 mA)=58.965.1 B; V _{WM} =85 B	DO-214AA, SMB	х∙х
68	SML4760	GS	dz	V ₂ (I ₂ =3.7 mA)=68 B; Z ₂₁ =150.0 Om	DO-214AC, SMA	K•A
68	U1ZB68	TOSH	dz	V ₂ (I ₂₇ = 4 mA) = 61.274.8 B; Z ₂₇ (I ₂₇ = 4 mA) < 1200m	DO-214AC SMA	K•A
68A	1.5SMC68AT3	MOT	VS.	V _{BB} (I _T = 1.0 mA) = 64.671.4B; V _{MM} = 58.1B; I _{PP} = 16.3A	DO-214AB SMC	K•A
68A	P6SMB68AT3	ON	VS VS	V _{BB} (I _T = 1 MA) = 64.671.4 B; V _{MM} = 92 B	DO-214AA, SMB	K•A
68C	P6SMB68CAT3	ON	vs vs	V _{BB} (I _T = 1 MA) = 64.671.4 B; V _{MM} = 92 B	DO-214AA, SMB	X • X
6P2	SML4735	GS	dz	V ₂ (I _Z =41.0mA)=6.2 B; Z _{ZI} =2.0 Om	DO-214AC, SMA	K•A
6P8	SML4736	GS	dz	$V_{Z}(I_{Z}=41.0MA)=6.2B$, $Z_{Z}=2.00M$ $V_{Z}(I_{Z}=37.0MA)=6.8B$; $Z_{ZT}=3.50M$	DO-214AC, SMA	K•A
6V8A	1.5SMC6.8AT3	MOT	7		DO-214AB, SMC	100000
OVÖA	1.05MC0.8A13	MUI	VS	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.457.14 \text{ B}; V_{WM} = 5.8 \text{ B}; I_{PP} = 143 \text{ A}$	DO-2 14AB, SMC	K∙A



Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2
6V8A	P6SMB6.8AT3	ON	vs	$V_{BR}(I_T = 10 \text{ mA}) = 6.457.14 \text{ B}; V_{WM} = 10.5 \text{ B}$	DO-214AA, SMB	K•A
7.5	U1ZB7.5	TOSH	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 6.88.3 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 300 \text{ m}$	DO-214AC, SMA	K•A
75	SML4761	GS	dz	V _Z (I _Z = 3.3 mA) = 75 B; Z _{ZT} = 175.0 Om	DO-214AC, SMA	K•A
75	U1ZB75	TOSH	dz	$V_Z(I_{ZT} = 4 \text{ mA}) = 67.582.5 \text{ B}; Z_{ZT}(I_{ZT} = 4 \text{ mA}) < 150 \text{ Om}$	DO-214AC, SMA	K•A
75A	1.5SMC75AT3	MOT	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 71.378.8 \text{ B}; V_{WM} = 64.1 \text{ B}; I_{PP} = 14.6 \text{ A}$	DO-214AB, SMC	K•A
75A	P6SMB75AT3	ON	VS	V _{BR} (I _T = 1 mA) = 71.378.8B; V _{MM} = 103B	DO-214AA, SMB	K•A
75C	P6SMB75CAT3	ON	vs	V _{BR} (I _T = 1 mA) = 71.378.8B; V _{MM} = 103B	DO-214AA, SMB	х∙х
7P5	SML4737	GS	dz	$V_Z(I_Z=34.0 \text{ mA})=7.5 \text{B}; Z_{ZT}=4.0 \text{ Cm}$	DO-214AC, SMA	K∙A
7V5A	1.5SMC7.5AT3	MOT	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 7.137.88 \text{ B}; V_{WM} = 6.4 \text{ B}; I_{pp} = 132 \text{ A}$	DO-214AB, SMC	K•A
7V5A	P6SMB7.5AT3	ON	vs	V _{BR} (I _T = 10 mA) = 7.137.88 B; V _{WM} = 11.3 B	DO-214AA, SMB	K∙A
8.2	U1ZB8.2	TOSH	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 7.49.1 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 300 \text{ m}$	DO-214AC, SMA	K•A
813B	1SMA5913BT3	ON	dz	$V_z(I_{zz} = 113.6 \text{ mA}) = 3.3 \text{ B}; Z_{zz} = 10.0 \text{ Om}$	DO-214AC, SMA	K•A
814B	1SMA5914BT3	ON	dz	$V_z(I_{zt} = 104.2 \text{ mA}) = 3.6 \text{ B}; Z_{zt} = 9.0 \text{ Om}$	DO-214AC, SMA	K•A
815B	1SMA5915BT3	ON	dz	$V_2(I_{2T} = 96.1 \text{ mA}) = 3.9 \text{ B}; Z_{2T} = 7.5 \text{ Om}$	DO-214AC, SMA	K•A
816B	1SMA5916BT3	ON	dz	$V_2(I_{2T} = 87.2 \text{ mA}) = 4.3 \text{ B}; Z_{2T} = 6.0 \text{ Om}$	DO-214AC, SMA	K•A
817B	1SMA5917BT3	ON	dz	$V_2(I_{ZT} = 79.8 \text{ mA}) = 4.7 \text{B}; Z_{ZT} = 5.0 \text{ Cm}$	DO-214AC, SMA	K•A
818B	1SMA5918BT3	ON	dz	$V_2(I_{2T} = 73.5 \text{ mA}) = 5.1 \text{B}; Z_{2T} = 4.0 \text{Om}$	DO-214AC, SMA	K•A
819B	1SMA5919BT3	ON	dz	$V_z(I_{ZT} = 66.9 \text{ mA}) = 5.6 \text{B}; Z_{ZT} = 2.0 \text{ Om}$	DO-214AC, SMA	K•A
82	SML4762	GS	dz	$V_7(I_7 = 3.0 \text{ mA}) = 82 \text{ B}; Z_{77} = 200.0 \text{ OM}$	DO-214AC, SMA	K•A
82	U1ZB82	TOSH	dz	$V_z(I_{zz} = 3 \text{ mA}) = 73.890.2 \text{ B}; Z_{zz}(I_{zz} = 3 \text{ mA}) < 170 \text{ Om}$	DO-214AC, SMA	K•A
820B	1SMA5920BT3	ON	dz	V _Z (I _{ZT} = 60.5 mA) = 6.2B; Z _{ZT} = 2.00m	DO-214AC, SMA	K•A
821B	1SMA5921BT3	ON	dz	V _Z (I _{ZT} = 55.1 mA) = 6.8 B; Z _{ZT} = 2.5 Om	DO-214AC, SMA	K•A
822B	1SMA5922BT3	ON	dz	$V_2(I_{2T} = 50.0 \text{ mA}) = 7.5 \text{ B}; Z_{2T} = 3.0 \text{ Om}$	DO-214AC, SMA	K•A
823B	1SMA5923BT3	ON	dz	V ₂ (I _{2T} = 45.7 mA) = 8.2B; Z _{2T} = 3.5 Om	DO-214AC, SMA	K•A
824B	1SMA5924BT3	ON	dz	V ₂ (I ₂₇ = 41.2 mA) = 9.1B; Z ₂₇ = 4.00m	DO-214AC, SMA	K•A
825B	1SMA5925BT3	ON	dz	V ₂ (I _{2T} = 37.5 mA) = 10 B; Z _{2T} = 4.5 Om	DO-214AC, SMA	K•A
826B	1SMA5926BT3	ON	dz	V _Z (I _{ZT} = 34.1 mA) = 11 B; Z _{ZT} = 5.5 Om	DO-214AC, SMA	K•A
827B	1SMA5927BT3	ON	dz	V ₂ (I _{2T} = 31.2 mA) = 12 B; Z _{2T} = 6.5 Om	DO-214AC, SMA	K•A
828B	1SMA5928BT3	ON	dz	V _z (I _{zT} = 28.8 mA) = 13 B; Z _{zT} = 7.0 Om	DO-214AC, SMA	K•A
829B	1SMA5929BT3	ON	dz	V _z (I _{zT} = 25.0 mA) = 15 B; Z _{zT} = 9.0 Om	DO-214AC, SMA	K•A
82A	1.5SMC82AT3	MOT	vs	V _{BR} (I _T = 1.0 mA) = 77.986.1B; V _{WM} = 70.1B; I _{PP} = 13.3A	DO-214AB, SMC	K•A
82A	P6SMB82AT3	ON	vs	V _{BR} (I _T = 1 mA) = 77.986.1B; V _{MM} = 113B	DO-214AA, SMB	K•A
82C	P6SMB82CAT3	ON	vs	V _{BB} (I _T = 1 mA) = 77.986.1B; V _{MM} = 113B	DO-214AA, SMB	х∙х
830B	1SMA5930BT3	ON	dz	V ₂ (I ₂₇ = 23.4 mA) = 16 B; Z ₂₇ = 10 Om	DO-214AC, SMA	K•A
831B	1SMA5931BT3	ON	dz	V ₂ (I _{2T} = 20.8 mA) = 18 B; Z _{2T} = 12 Om	DO-214AC, SMA	K•A
832B	1SMA5932BT3	ON	dz	V ₇ (I _{2T} = 18.7 mA) = 20 B; Z _{2T} = 14 Om	DO-214AC, SMA	K•A
833B	1SMA5933BT3	ON	dz	V ₂ (I _{2T} = 17.0 mA) = 22 B; Z _{2T} = 17.5 Om	DO-214AC, SMA	K•A
834B	1SMA5934BT3	ON	dz	V _z (I _{zz} = 15.6 mA) = 24 B; Z _{zz} = 19 Om	DO-214AC, SMA	K•A
835B	1SMA5935BT3	ON	dz	V _Z (I _{ZT} = 13.9 mA) = 27 B; Z _{ZT} = 23 Om	DO-214AC, SMA	K•A
836B	1SMA5936BT3	ON	dz	V _Z (I _{ZT} = 12.5 mA) = 30 B; Z _{ZT} = 26 Om	DO-214AC, SMA	K•A
837B	1SMA5937BT3	ON	dz	V ₂ (I _{2T} = 11.4 mA) = 33 B; Z _{2T} = 33 Om	DO-214AC, SMA	K•A
838B	1SMA5938BT3	ON	dz	V _Z (I _{ZT} = 10.4 mA) = 36 B; Z _{ZT} = 38 Om	DO-214AC, SMA	K•A
839B	1SMA5939BT3	ON	dz	V ₂ (I ₂₇ = 9.6 mA) = 39B; Z ₂₇ = 45 Om	DO-214AC, SMA	K•A
840B	1SMA5940BT3	ON	dz	$V_Z(I_{ZT} = 8.7 \text{ mA}) = 43 \text{ B}, Z_{ZT} = 53 \text{ OM}$	DO-214AC, SMA	K•A
841B	1SMA5941BT3	ON	dz	$V_2(I_{27} = 8.0 \text{ mA}) = 478; Z_{27} = 67 \text{ cm}$	DO-214AC, SMA	K•A
842B	1SMA5942BT3	ON	dz	$V_2(I_{27} = 7.3 \text{ mA}) = 51 \text{ B}; Z_{27} = 70 \text{ cm}$	DO-214AC, SMA	K•A
843B	1SMA5943BT3	ON	dz	V ₂ (I _{ZT} = 6.7 MA) = 56B; Z _{ZT} = 76 CM	DO-214AC, SMA	K•A
844B	1SMA5944BT3	ON	dz	V ₂ (I _{2T} = 6.0 mA) = 62B; Z _{2T} = 100 Om	DO-214AC, SMA	K•A
845B	1SMA5945BT3	ON	dz	V _Z (I _{ZT} = 0.5 MA) = 68 B; Z _{ZT} = 100 OM	DO-214AC, SMA	K•A
8P2	SML4738	GS	dz	V ₂ (I _{ZT} = 3.5 MA) = 68B; Z _{ZT} = 1.20 GM V ₂ (I _Z = 31.0 MA) = 8.2B; Z _{ZT} = 4.5 GM	DO-214AC, SMA	K•A
8V2A	1.5SMC8.2AT3	MOT	VS	V _{BS} (I _T = 10.0 mA) = 7.798.61 B; V _{MM} = 7.02 B; I _{PP} = 124 A	DO-214AB, SMC	K•A
8V2A	P6SMB8.2AT3	ON	vs vs	V _{BR} (I _T = 10.0MA) = 7.798.61 B; V _{MM} = 7.02 B; I _{PP} = 124 A V _{BR} (I _T = 10 MA) = 7.798.61 B; V _{MM} = 12.1 B	DO-214AB, SMC	K•A
9.1	U1ZB9.1	TOSH			DO-214AA, SMB DO-214AC, SMA	K•A
9.1	0 IZB9. I	IUSH	UZ	$V_Z(I_{ZT} = 10 \text{ mA}) = 8.210.1 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 30 \text{ Om}$	DU-214AU, SMA	K-A





Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2
91	SML4763	GS	dz	V _Z (I _Z =2.0mA)=91 B; Z _{Z1} =250.0 Om	DO-214AC, SMA	K•A
913B	1SMB5913BT3	ON	dz	V _Z (I _{ZT} = 113.6 mA) = 3.3 B; Z _{ZT} = 10.0 Om	DO-214AA, SMB	K•A
914B	1SMB5914BT3	ON	dz	$V_Z(I_{ZT} = 104.2 \text{ mA}) = 3.6 \text{B}; Z_{ZT} = 9.0 \text{ Om}$	DO-214AA, SMB	K•A
915B	1SMB5915BT3	ON	dz	$V_Z(I_{ZT}=96.1 \text{ mA})=3.9 \text{ B}; Z_{ZT}=7.5 \text{ Om}$	DO-214AA, SMB	K•A
916B	1SMB5916BT3	ON	dz	$V_Z(I_{ZT} = 87.2 \text{ mA}) = 4.3 \text{ B}; Z_{ZT} = 6.0 \text{ Om}$	DO-214AA, SMB	K•A
917B	1SMB5917BT3	ON	dz	$V_Z(I_{ZI} = 79.8 \text{ mA}) = 4.7 \text{ B}; Z_{ZI} = 5.0 \text{ OM}$	DO-214AA, SMB	K•A
918B	1SMB5918BT3	ON	dz	V _Z (I _{ZT} = 73.5 mA) = 5.1 B; Z _{ZT} = 4.0 Om	DO-214AA, SMB	K•A
919B	1SMB5919BT3	ON	dz	V _Z (I _{ZT} = 66.9 mA) = 5.6 B; Z _{ZT} = 2.0 Om	DO-214AA, SMB	K•A
91A	1.5SMC91AT3	MOT	VS	V _{BR} (I _T = 1.0 mA) = 86.595.5B; V _{WM} = 77.8B; I _{PP} = 12A	DO-214AB, SMC	K•A
91A	P6SMB91AT3	ON	VS	V _{BB} (I _T = 1 MA) = 86.595.5 B; V _{WM} = 125B	DO-214AA, SMB	K•A
91C	P6SMB91CAT3	ON	vs	V _{BB} (I _T = 1 mA) = 86.595.5 B; V _{WM} = 125B	DO-214AA, SMB	х∙х
920B	1SMB5920BT3	ON	dz	$V_Z(I_{ZI} = 60.5 \text{ mA}) = 6.2 \text{B}; Z_{ZI} = 2.00 \text{m}$	DO-214AA, SMB	K•A
921B	1SMB5921BT3	ON	dz	$V_z(I_{zT}=55.1 \text{ mA})=6.8 \text{ B; } Z_{zT}=2.5 \text{ Om}$	DO-214AA, SMB	K•A
922B	1SMB5922BT3	ON	dz	$V_z(I_{zz} = 50.0 \text{ mA}) = 7.5 \text{ B}; Z_{zz} = 3.00 \text{ m}$	DO-214AA SMB	K•A
923B	1SMB5923BT3	ON	dz	$V_z (I_{ZI} = 45.7 \text{ mA}) = 8.2 \text{B}; Z_{ZI} = 3.50 \text{m}$	DO-214AA, SMB	K•A
924B	1SMB5924BT3	ON	dz	$V_2(I_{ZT}=41.2 \text{ mA})=9.1 \text{ B; } Z_{ZT}=4.0 \text{ Om}$	DO-214AA SMB	K•A
925B	1SMB5925BT3	ON	dz	$V_2(I_{ZT}=37.5 \text{ mA})=10 \text{ B}; Z_{ZT}=4.5 \text{ Om}$	DO-214AA, SMB	K•A
926B	1SMB5926BT3	ON	dz	V ₂ (I ₂₇ = 34.1 mA) = 11B; Z ₂₇ = 5.5 Om	DO-214AA SMB	K•A
927B	1SMB5927BT3	ON	dz	V _z (I _{zT} = 31.2 mA) = 12B; Z _{zT} = 6.5 Om	DO-214AA, SMB	K•A
928B	1SMB5928BT3	ON	dz	V _Z (I _{ZT} = 28.8 mA) = 13 B; Z _{ZT} = 7.0 Om	DO-214AA SMB	K•A
929B	1SMB5929BT3	ON	dz	V _Z (I _{ZT} = 25.0 mA) = 15B; Z _{ZT} = 9.0 Om	DO-214AA, SMB	K•A
930B	1SMB5930BT3	ON	dz	V _Z (I _{ZT} = 23.4 mA) = 16B; Z _{ZT} = 100m	DO-214AA, SMB	K•A
931B	1SMB5931BT3	ON	dz	V _Z (I _{ZT} = 20.8 mA) = 18B; Z _{ZT} = 12Om	DO-214AA, SMB	K•A
932B	1SMB5932BT3	ON	dz	$V_2(I_{ZI} = 18.7 \text{ mA}) = 20 \text{ B; } Z_{ZI} = 140 \text{ m}$	DO-214AA SMB	K•A
933B	1SMB5933BT3	ON	dz	$V_2(I_{Z1} = 17.0 \text{ mA}) = 22 \text{B; } Z_{Z1} = 17.5 \text{ Om}$	DO-214AA SMB	K•A
934B	1SMB5934BT3	ON	dz	V _Z (I _{ZT} = 15.6 mA) = 24B; Z _{ZT} = 190m	DO-214AA SMB	K•A
935B	1SMB5935BT3	ON	dz	$V_2(I_{27} = 13.9 \text{ mA}) = 27 \text{ B; } Z_{27} = 230 \text{ m}$	DO-214AA SMB	K•A
936B	1SMB5936BT3	ON	dz	$V_Z(I_{ZT} = 12.5 \text{ mA}) = 30 \text{ B; } Z_{ZT} = 280 \text{ m}$	DO-214AA SMB	K•A
937B	1SMB5937BT3	ON	dz	$V_z(I_{zz} = 11.4 \text{ mA}) = 33 \text{ B; } Z_{zz} = 330 \text{ m}$	DO-214AA SMB	K•A
938B	1SMB5938BT3	ON	dz	$V_Z(I_{ZT} = 10.4 \text{ mA}) = 36 \text{ B; } Z_{ZT} = 38 \text{ Om}$	DO-214AA SMB	K•A
939B	1SMB5939BT3	ON	dz	$V_Z(I_{ZT} = 9.6 \text{ mA}) = 39 \text{ B; } Z_{ZT} = 450 \text{ m}$	DO-214AA SMB	K•A
940B	1SMB5940BT3	ON	dz	V _Z (I _{ZT} = 8.7 mA) = 43B; Z _{ZT} = 530m	DO-214AA, SMB	K•A
941B	1SMB5941BT3	ON	dz	V ₂ (I _{2T} = 8.0 mA) = 47B; Z _{2T} = 670m	DO-214AA, SMB	K•A
942B	1SMB5942BT3	ON	dz	$V_Z(I_{ZI} = 7.3 \text{ mA}) = 51 \text{ B; } Z_{ZI} = 70 \text{ cm}$	DO-214AA, SMB	K•A
943B	1SMB5943BT3	ON	dz	V _Z (I _{ZT} = 6.7 mA) = 56B; Z _{ZT} = 86Om	DO-214AA, SMB	K•A
944B	1SMB5944BT3	ON	dz	$V_Z(I_{ZI} = 6.0 \text{ mA}) = 62 \text{ B; } Z_{ZI} = 100 \text{ OM}$	DO-214AA, SMB	K•A
945B	1SMB5945BT3	ON	dz	V _Z (I _{ZT} = 5.5 mA) = 68 B; Z _{ZT} = 120 Om	DO-214AA, SMB	K•A
946B	1SMB5946BT3	ON	dz	$V_Z(I_{ZI} = 5.0 \text{ mA}) = 75 \text{ B; } Z_{ZI} = 1400 \text{ m}$	DO-214AA, SMB	K•A
947B	1SMB5947BT3	ON	dz	V _Z (I _{ZI} = 4.6 mA) = 82 B; Z _{ZI} = 160 Om	DO-214AA, SMB	K•A
948B	1SMB5948BT3	ON	dz	V _Z (I _{ZT} = 4.1 mA) = 91 B; Z _{ZT} = 200 Om	DO-214AA SMB	K•A
949B	1SMB5946BT3	ON	dz	V _Z (I _{ZT} = 4. 1 NA) = 91B, Z _{ZT} = 200 OM V _Z (I _{ZT} = 3.7 NA) = 100 B; Z _{ZT} = 250 OM	DO-214AA, SMB	K•A
950B	1SMB5949BT3	ON	dz	V _Z ((_{ZT} = 3.4 mA) = 110 B; Z _{ZT} = 230 OM	DO-214AA, SMB	K•A
951B	1SMB5951BT3	ON	dz	V _Z ((ZT = 3.1 mA) = 110B; ZZT = 300 CM	DO-214AA, SMB	K•A
952B	1SMB5951BT3	ON	dz	V _Z ((ZT = 3.1 MA) = 120B, ZZT = 300 CM V _Z ((ZT = 2.9 MA) = 130B; ZZT = 450 CM	DO-214AA, SMB	K•A
953B	1SMB5952BT3	ON	_		DO-214AA, SMB	K•A
		ON	dz	V _Z (I _{ZT} = 2.5 MA) = 150 B; Z _{ZT} = 600 OM	DO-214AA, SMB	
954B	1SMB5954BT3		dz	$V_Z(I_{ZT} = 2.3 \text{ mA}) = 160 \text{ B}; Z_{ZT} = 700 \text{ CM}$		K•A
955B 956B	1SMB5955BT3	ON	dz	V _Z (I _{ZT} = 2.1 mA) = 180 B; Z _{ZT} = 900 Om	DO-214AA, SMB	K•A K•A
956B	1SMB5956BT3	ON GS	dz	V _Z (I _{ZT} = 1.9 MA) = 200 B; Z _{ZT} = 1200 OM	DO-214AA, SMB	
20000	SML4739	-	dz	V _Z (I _Z =28.0 mA)=9.1 B; Z _{ZT} =5.0 Om	DO-214AC, SMA	K•A
9V1A	1.5SMC9.1AT3	MOT	VS	V _{BR} (I _T = 10.0 mA) = 8.659.55 B; V _{WM} = 7.78 B; I _{PP} = 112 A	DO-214AB, SMC	K•A
9V1A	P6SMB9.1AT3	ON	VS -1"	V _{BR} (I _T = 1 MA) = 8.659.55 B; V _{WM} = 13.4 B	DO-214AA, SMB	K•A
A6	BAS216	PHIL	di	$V_R < 75B$; $I_F < 250m$ A; $V_F (I_F = 150m$ A) $< 1.25B$; $I_R < 50m$ KA; $C_D < 1.5n$ \Phi; $I_{RR} < 4H$ C	SOD-110	K∙A



Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2
AD	SMBJ5.0C	VISH	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.407.55 \text{ B}; V_{WM} = 5.0 \text{ B}; I_{PP} = 62.5 \text{ A}$	DO-214AA, SMB	х∙х
ADP	TPSMA6.8	GS	٧S	V _{BR} (I _T = 10.0 mA) = 6.127.48 B; V _{WM} = 5.50 B; I _{PP} = 37.0 A	DO-214AC, SMA	K•A
AE	SMBJ5.0CA	VISH	VS	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.407.23 \text{ B}; V_{WM} = 5.0 \text{ B}; I_{pp} = 65.2 \text{ A}$	DO-214AA, SMB	x•x
AEP	TPSMA6.8A	GS	νs	V _{BR} (I _T = 10.0 mA) = 6.457.14 B; V _{WM} = 5.80 B; I _{PP} = 38.1 A	DO-214AC, SMA	K•A
AF	SMBJ6.0C	VISH	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.678.45 \text{ B}; V_{WM} = 6.0 \text{ B}; I_{pp} = 52.6 \text{ A}$	DO-214AA, SMB	х∙х
AFP	TPSMA7.5	GS	٧S	V _{BR} (I _T = 10.0 mA) = 6.758.25 B; V _{WM} = 6.05 B; I _{PP} = 34.2 A	DO-214AC, SMA	K•A
AG	SMBJ6.0CA	VISH	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.677.67 \text{ B}; V_{WM} = 6.0 \text{ B}; I_{PP} = 58.3 \text{ A}$	DO-214AA, SMB	χ•χ
AGP	TPSMA7.5A	GS	VS	V _{BR} (I _T = 10.0 mA) = 7.137.88 B; V _{WM} = 6.40 B; I _{PP} = 35.4 A	DO-214AC, SMA	K∙A
AH	SMBJ6.5C	VISH	VS	$V_{BR}(I_T = 10.0 \text{ mA}) = 7.229.14 \text{ B}; V_{WM} = 6.5 \text{ B}; I_{pp} = 48.7 \text{ A}$	DO-214AA, SMB	x•x
AHP	TPSMA8.2	GS	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 7.389.02 \text{ B}; V_{WM} = 6.63 \text{ B}; I_{PP} = 32.0 \text{ A}$	DO-214AC, SMA	K•A
AK	SMBJ6.5CA	VISH	vs	$V_{BB}(I_T = 10.0 \text{ mA}) = 7.228.30 \text{ B}; V_{WM} = 6.5 \text{ B}; I_{PP} = 53.6 \text{ A}$	DO-214AA, SMB	х∙х
AKP	TPSMA8.2A	GS	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 7.798.61 \text{ B}; V_{WM} = 7.02 \text{ B}; I_{PP} = 33.1 \text{ A}$	DO-214AC, SMA	K•A
AL	SMBJ7.0C	VISH	VS.	$V_{BR}(I_T = 10.0 \text{ mA}) = 7.789.86 \text{ B}; V_{WM} = 7.0 \text{ B}; I_{pp} = 45.1 \text{ A}$	DO-214AA, SMB	X • X
ALP	TPSMA9.1	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 8.1910.00 \text{ B}; V_{WM} = 7.37 \text{ B}; I_{PP} = 29.0 \text{ A}$	DO-214AC, SMA	K•A
AM	SMBJ7.0CA	VISH	VS	$V_{BR}(I_T = 10.0 \text{ mA}) = 7.788.95 \text{ B}; V_{WM} = 7.0 \text{ B}; I_{pp} = 50.0 \text{ A}$	DO-214AA, SMB	х∙х
AMP	TPSMA9.1A	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 8.659.55 \text{ B}; V_{WM} = 7.78 \text{ B}; I_{PP} = 29.9 \text{ A}$	DO-214AC, SMA	K•A
AN	SMBJ7.5C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 8.3310.80 \text{ B; } V_{WM} = 7.5 \text{ B; } I_{pp} = 42.0 \text{ A}$	DO-214AA, SMB	χ•χ
ANP	TPSMA10	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 9.0011.00 \text{ B}; V_{WM} = 8.10 \text{ B}; I_{PP} = 26.7 \text{ A}$	DO-214AC, SMA	K•A
AP	SMBJ7.5CA	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 8.339.58 \text{ B}; V_{WM} = 7.5 \text{ B}; I_{PP} = 46.5 \text{ A}$	DO-214AA, SMB	x•x
APP	TPSMA10A	GS	VS	V _{BR} (I _T = 1.0 mA) = 9.5010.50 B; V _{WM} = 8.65 B; I _{PP} = 27.6 A	DO-214AC, SMA	K•A
AQ	SMBJ8.0C	VISH	٧S	V _{BR} (I _T = 1.0 mA) = 8.8911.30 B; V _{WM} = 8.0 B; I _{PP} = 40.0 A	DO-214AA, SMB	х∙х
AQP	TPSMA11	GS	vs	V _{BR} (I _T = 1.0 mA) = 9.9012.10 B; V _{WM} = 8.92 B; I _{PP} = 24.7 A	DO-214AC, SMA	K•A
AR	SMBJ8.0CA	VISH	vs	V _{BR} (I _T = 1.0 mA) = 8.8910.23 B; V _{MM} = 8.0 B; I _{PP} = 44.1 A	DO-214AA, SMB	х∙х
ARP	TPSMA11A	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 10.5011.60 \text{ B}; V_{WM} = 9.40 \text{ B}; I_{pp} = 25.6 \text{ A}$	DO-214AC, SMA	K•A
AS	SMBJ8.5C	VISH	vs	V _{BR} (I _T = 1.0 mA) = 9.4411.92 B; V _{WM} = 8.5 B; I _{PP} = 37.7 A	DO-214AA, SMB	х∙х
ASP	TPSMA12	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 10.8013.20 \text{ B}; V_{WM} = 9.72 \text{ B}; I_{PP} = 23.1 \text{ A}$	DO-214AC, SMA	K•A
AT	SMBJ8.5CA	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 9.4410.82 \text{ B; } V_{WM} = 8.5 \text{ B; } I_{pp} = 41.7 \text{ A}$	DO-214AA, SMB	x•x
ATP	TPSMA12A	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 11.4012.60 \text{ B}; V_{WM} = 10.20 \text{ B}; I_{PP} = 24.0 \text{ A}$	DO-214AC, SMA	K•A
AU	SMBJ9.0C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 10.0012.80 \text{ B}; V_{WM} = 9.0 \text{ B}; I_{PP} = 35.5 \text{ A}$	DO-214AA, SMB	x•x
AUP	TPSMA13	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 11.7014.30 \text{ B}; V_{MM} = 10.50 \text{ B}; I_{PP} = 21.1 \text{ A}$	DO-214AC, SMA	K•A
AV	pSMBJ9.0CA	VISH	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 10.0011.50 \text{ B}; V_{WM} = 9.0 \text{ B}; I_{PP} = 39.0 \text{ A}$	DO-214AA, SMB	х∙х
AVP	TPSMA13A	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 12.4013.70 \text{ B}; V_{WM} = 11.10 \text{ B}; I_{PP} = 22.0 \text{ A}$	DO-214AC, SMA	K•A
AW	SMBJ10C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 11.1014.10 \text{ B}; V_{WM} = 10.0 \text{ B}; I_{PP} = 31.9 \text{ A}$	DO-214AA, SMB	х∙х
AWP	TPSMA15	GS	VS	V _{BR} (I _T = 1.0 mA) = 13.5016.30 B; V _{WM} = 12.10 B; I _{PP} = 18.2 A	DO-214AC, SMA	K•A
AX	SMBJ10CA	VISH	٧S	V _{BR} (I _T = 1.0 mA) = 11.1012.80 B; V _{WM} = 10.0 B; I _{PP} = 35.3 A	DO-214AA, SMB	х∙х
AXP	TPSMA15A	GS	٧S	V _{BR} (I _T = 1.0 mA) = 14.3015.80 B; V _{WM} = 12.80 B; I _{pp} = 18.9 A	DO-214AC, SMA	K•A
AY	SMBJ11C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 12.2015.40 \text{ B}; V_{WM} = 11.0 \text{ B}; I_{pp} = 29.9 \text{ A}$	DO-214AA, SMB	χ•χ
AYP	TPSMA16	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 14.4017.60 \text{ B}; V_{WM} = 12.90 \text{ B}; I_{PP} = 17.0 \text{ A}$	DO-214AC, SMA	K•A
AZ	SMBJ11CA	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 12.2014.40 \text{ B}; V_{WM} = 11.0 \text{ B}; I_{pp} = 33.0 \text{ A}$	DO-214AA, SMB	x•x
AZP	TPSMA16A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 15.2016.80 \text{ B}; V_{WM} = 13.60 \text{ B}; I_{PP} = 17.8 \text{ A}$	DO-214AC, SMA	K•A
BD	SMBJ12C	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 13.3016.90 \text{ B}; V_{WM} = 12.0 \text{ B}; I_{pp} = 27.3 \text{ A}$	DO-214AA, SMB	х∙х
BDD	SMCJ5.0C	VISH	vs	V _{BR} (I _T = 10.0 mA) = 6.407.55 B; V _{WM} = 5.0 B; I _{PP} = 156.2 A	DO-214AB, SMC	x•x
BDE	SMCJ5.0CA	VISH	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.407.25 \text{ B}; V_{WM} = 5.0 \text{ B}; I_{pp} = 163.0 \text{ A}$	DO-214AB, SMC	х∙х
BDF	SMCJ6.0C	VISH	VS	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.678.45 \text{ B}; V_{WM} = 6.0 \text{ B}; I_{pp} = 131.6 \text{ A}$	DO-214AB, SMC	х∙х
BDG	SMCJ6.0CA	VISH	vs	V _{BR} (I _T = 10.0 mA) = 6.677.67 B; V _{WM} = 6.0 B; I _{PP} = 145.6 A	DO-214AB, SMC	х∙х
BDH	SMCJ6.5C	VISH	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 7.229.14 \text{ B}; V_{WM} = 6.5 \text{ B}; I_{PP} = 122.0 \text{ A}$	DO-214AB, SMC	x•x
BDK	SMCJ6.5CA	VISH	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 7.228.30 \text{ B}; V_{WM} = 6.5 \text{ B}; I_{PP} = 133.9 \text{ A}$	DO-214AB, SMC	x•x
BDL	SMCJ7.0C	VISH	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 7.789.86 \text{ B}; V_{WM} = 7.0 \text{ B}; I_{pp} = 112.8 \text{ A}$	DO-214AB, SMC	х∙х
BDM	SMCJ7.0CA	VISH	vs	V _{BR} (I _T = 10.0 mA) = 7.788.95 B; V _{WM} = 7.0 B; I _{PP} = 125.0 A	DO-214AB, SMC	х∙х
BDN	SMCJ7.5C	VISH	νs	V _{BR} (I _T = 1.0 mA) = 8.3310.80 B; V _{WM} = 7.5 B; I _{PP} = 104.9 A	DO-214AB, SMC	χ●χ
BDP	SMCJ7.5CA	VISH	νs	V _{BR} (I _T = 1.0 mA) = 8.339.58 B; V _{WM} = 7.5 B; I _{PP} = 116.3 A	DO-214AB, SMC	х∙х
BDP	TPSMA18	GS	vs	V _{BR} (I _T = 1.0 mA) = 16.2019.80 B; V _{MM} = 14.50 B; I _{PP} = 15.1 A	DO-214AC, SMA	K•A
BDQ	SMCJ8.0C	VISH	vs	V _{BR} (I _T = 1.0 mA) = 8.8911.30 B; V _{WM} = 8.0 B; I _{PP} = 100.0 A	DO-214AB, SMC	х∙х





Код	Типономинал	6	Φ	Особенности	Корпус	Ц:1•2
BDR	SMCJ8.0CA	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 8.8910.23 \text{ B}; V_{WM} = 8.0 \text{ B}; I_{PP} = 110.3 \text{ A}$	DO-214AB, SMC	х∙х
BDS	SMCJ8.5C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 9.4411.92 \text{ B}; V_{WM} = 8.5 \text{ B}; I_{PP} = 94.3 \text{ A}$	DO-214AB, SMC	х∙х
BDT	SMCJ8.5CA	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 9.4410.82 \text{ B}; V_{WM} = 8.5 \text{ B}; I_{PP} = 104.2 \text{ A}$	DO-214AB, SMC	х∙х
BDU	SMCJ9.0C	VISH	VS	V _{BR} (I _T = 1.0 mA) = 10.0012.80 B; V _{WM} = 9.0 B; I _{PP} = 88.7 A	DO-214AB, SMC	х∙х
BDV	SMCJ9.0CA	VISH	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 10.0011.50 \text{ B}; V_{WM} = 9.0 \text{ B}; I_{PP} = 97.4 \text{ A}$	DO-214AB, SMC	х∙х
BDW	SMCJ10C	VISH	VS	V _{BR} (I _T = 1.0 mA) = 11.1014.10 B; V _{WM} = 10.0 B; I _{PP} = 79.8 A	DO-214AB, SMC	χ●χ
BDX	SMCJ10CA	VISH	VS	V _{BR} (I _T = 1.0 mA) = 11.1012.80 B; V _{WM} = 10.0B; I _{PP} = 88.2 A	DO-214AB, SMC	х∙х
BDY	SMCJ11C	VISH	VS	V _{BB} (I _T = 1.0 mA) = 12.2015.40 B; V _{WM} = 11.0B; I _{PP} = 74.6 A	DO-214AB, SMC	х∙х
BDZ	SMCJ11CA	VISH	VS	V _{BR} (I _T = 1.0 mA) = 12.2014.40 B; V _{WM} = 11.0B; I _{PP} = 82.4 A	DO-214AB, SMC	x•x
BE	SMBJ12CA	VISH	VS	V _{BB} (I _T = 1.0 mA) = 13.3015.30 B; V _{WM} = 12.0 B; I _{PP} = 30.2 A	DO-214AA, SMB	х∙х
BED	SMCJ12C	VISH	VS	V _{BB} (I _T = 1.0 mA) = 13.3016.90 B; V _{WM} = 12.0B; I _{PP} = 68.2 A	DO-214AB, SMC	х∙х
BEE	SMCJ12CA	VISH	VS	V _{BB} (I _T = 1.0 mA) = 13.3015.30 B; V _{MM} = 12.0B; I _{PP} = 75.3 A	DO-214AB, SMC	х∙х
BEF	SMCJ13C	VISH	VS	V _{BB} (I _T = 1.0 mA) = 14.4018.20 B; V _{WM} = 13.0 B; I _{PP} = 63.0 A	DO-214AB, SMC	х∙х
BEG	SMCJ13CA	VISH	VS	V _{BB} (I _T = 1.0 mA) = 14.4016.50 B; V _{WM} = 13.0 B; I _{PP} = 69.7 A	DO-214AB, SMC	х∙х
BEH	SMCJ14C	VISH	VS	V _{BB} (I _T = 1.0 mA) = 15.6019.80 B; V _{WM} = 14.0 B; I _{PP} = 58.1 A	DO-214AB, SMC	х∙х
BEK	SMCJ14CA	VISH	VS	V _{BB} (I _T = 1.0 mA) = 15.6017.90 B; V _{MM} = 14.0 B; I _{PP} = 64.7 A	DO-214AB, SMC	х∙х
BEL	SMCJ15C	VISH	VS	V _{BB} (I _T = 1.0 mA) = 16.7021.10 B; V _{MM} = 15.0 B; I _{PP} = 55.8 A	DO-214AB, SMC	х∙х
BEM	SMCJ15CA	VISH	VS	V _{BR} (I _T = 1.0 MA) = 16.7019.20 B; V _{MM} = 15.0B; I _{PP} = 61.5 A	DO-214AB, SMC	х∙х
BEN	SMCJ16C	VISH	VS	V _{BB} (I _T = 1.0 MA) = 17.8022.60 B; V _{MM} = 16.0 B; I _{PP} = 52.1 A	DO-214AB, SMC	х∙х
BEP	SMCJ16CA	VISH	VS	V _{BB} (I _T = 1.0 mA) = 17.8020.50 B; V _{MM} = 16.0 B; I _{PP} = 57.7 A	DO-214AB, SMC	x•x
BEP	TPSMA18A	GS	VS	V _{BR} (I _T = 1.0 mA) = 17.1018.90 B; V _{MM} = 15.30 B; I _{PP} = 15.9 A	DO-214AC, SMA	K•A
BEQ	SMCJ17C	VISH	VS	V _{BB} (I _T = 1.0 mA) = 18.9023.90 B; V _{MM} = 17.0B; I _{PP} = 49.2 A	DO-214AB, SMC	х∙х
BER	SMCJ17CA	VISH	VS	V _{BB} (I _T = 1.0 mA) = 18.9021.70 B; V _{WM} = 17.0B; I _{PP} = 53.3 A	DO-214AB, SMC	х∙х
BES	SMCJ18C	VISH	VS	V _{BR} (I _T = 1.0 MA) = 20.0025.30 B; V _{WM} = 18.0B; I _{PP} = 46.6A	DO-214AB, SMC	x•x
BET	SMCJ18CA	VISH	vs	V _{BB} (I _T = 1.0 MA) = 20.0023.30 B; V _{WM} = 18.0B; I _{PP} = 51.4A	DO-214AB. SMC	x•x
BEU	SMCJ20C	VISH	vs	V _{BB} (I _T = 1.0 mA) = 22.2028.10 B; V _{WM} = 20.0B; I _{PP} = 41.9 A	DO-214AB, SMC	x•x
BEV	SMCJ20CA	VISH	VS	V _{BB} (I _T = 1.0 mA) = 22.2025.50 B; V _{WM} = 20.0B; I _{PP} = 46.3 A	DO-214AB, SMC	x•x
BEW	SMCJ22C	VISH	VS	V _{BB} (I _T = 1.0 mA) = 24.4030.90 B; V _{WM} = 22.0B; I _{PP} = 38.1 A	DO-214AB, SMC	x•x
BEX	SMCJ22CA	VISH	VS	V _{BB} (I _T = 1.0 mA) = 24.4028.00 B; V _{WM} = 22.0 B; I _{PP} = 42.2 A	DO-214AB, SMC	x•x
BEY	SMCJ24C	VISH	VS	V _{BB} (I _T = 1.0 mA) = 26.7033.80 B; V _{MM} = 24.0B; I _{EP} = 34.9 A	DO-214AB, SMC	x•x
BEZ	SMCJ24CA	VISH	VS	V _{BB} (I _T = 1.0 MA) = 26.7030.70 B; V _{MM} = 24.0B; I _{EP} = 38.6 A	DO-214AB, SMC	x•x
BF	SMBJ13C	VISH	VS	V _{BR} (I _T = 1.0 mA) = 14.4018.20 B; V _{MM} = 13.0B; I _{PP} = 25.2 A	DO-214AA SMB	x•x
BFD	SMCJ26C	VISH	VS	V _{BB} (I _T = 1.0 mA) = 28.9036.80 B; V _{MM} = 26.0B; I _{EP} = 32.2 A	DO-214AB, SMC	x•x
BFE	SMCJ26CA	VISH	VS	V _{BB} (I _T = 1.0 mA) = 28.9033.20 B; V _{WM} = 26.0 B; I _{PP} = 35.6 A	DO-214AB, SMC	X•X
BFF	SMCJ28C	VISH	VS	V _{BB} (I _T = 1.0 MA) = 31.1039.40 B; V _{MM} = 28.0B; I _{SP} = 30.0 A	DO-214AB, SMC	X•X
BFG	SMCJ28CA	VISH	VS	V _{BB} (I _T = 1.0 MA) = 31.1035.80 B; V _{WM} = 28.0B; I _{PP} = 33.0 A	DO-214AB, SMC	X • X
BFH	SMCJ30C	VISH	VS	V _{BB} (I _T = 1.0 MA) = 33.3042.40 B; V _{MM} = 30.0B; I _{DP} = 28.0 A	DO-214AB, SMC	x•x
BFK	SMCJ30CA	VISH	VS	V _{BB} (I _T = 1.0 mA) = 33.3038.30 B; V _{MM} = 30.0B; I _{PP} = 31.0 A	DO-214AB, SMC	X•X
BFL	SMCJ33C	VISH	VS	V _{BB} (I _T = 1.0 MA) = 36.7046.90 B; V _{MM} = 33.0B; I _{PP} = 25.2 A	DO-214AB, SMC	X • X
BFM	SMCJ33CA	VISH	VS	V _{BB} (I _T = 1.0 MA) = 36.7042.20 B; V _{MM} = 33.0B; I _{PP} = 28.1 A	DO-214AB, SMC	X•X
BFN	SMCJ36C	VISH	VS	V _{BB} (I _T = 1.0 MA) = 40.0050.70 B; V _{WM} = 36.0 B; I _{PP} = 23.3 A	DO-214AB, SMC	X • X
BFP	SMCJ36CA	VISH	VS	V _{BB} (I _T = 1.0 MA) = 40.0046.00 B; V _{WM} = 36.0 B; I _{PP} = 25.8 A	DO-214AB, SMC	X•X
BFP	TPSMA20	GS	VS VS	V _{BR} (I _T = 1.0 mA) = 18.0022.00 B; V _{WM} = 16.20 B; I _{PP} = 23.7 A	DO-214AC, SMA	K•A
BFQ	SMCJ40C	VISH	VS VS	V _{BR} (I _T = 1.0 MA) = 44.4056.30 B; V _{MM} = 40.0B; I _{PP} = 21.0 A	DO-214AB, SMC	X•X
BFR	SMCJ40CA	VISH	vs vs	The state of the s	DO-214AB, SMC	X•X
BFS	SMCJ43C	VISH	VS VS	V _{BR} (I _T = 1.0 mA) = 44.4051.10 B; V _{MM} = 40.0 B; I _{pp} = 23.2 A V _m (I _m = 1.0 mA) = 47.8060.50 B; V _m = 43.0 B; I _m = 19.6 A	DO-214AB, SMC	X • X
BFT	SMCJ43CA	VISH	VS VS	V _{BR} (I _T = 1.0 mA) = 47.8060.50 B; V _{WM} = 43.0 B; I _{PP} = 19.6 A	DO-214AB, SMC	χ• χ
BFU	SMCJ45CA SMCJ45C	VISH	VS VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 47.8054.90 \text{ B}; V_{MM} = 43.0 \text{ B}; I_{PP} = 21.6 \text{ A}$ $V_{BR}(I_T = 1.0 \text{ mA}) = 50.0063.30 \text{ B}; V_{MM} = 45.0 \text{ B}; I_{PP} = 18.7 \text{ A}$	DO-214AB, SMC	x•x
BFV	SMCJ45CA	VISH	-	The state of the s		x•x
BFW	SMCJ48C	VISH	VS VS	$V_{BR}(I_T = 1.0 \text{ MA}) = 50.0057.50 \text{ B; } V_{MM} = 45.0 \text{ B; } I_{PP} = 20.6 \text{ A}$	DO-214AB, SMC DO-214AB, SMC	x•x
BFX	SMCJ48CA SMCJ48CA	VISH	VS VS	V _{BR} (I _T = 1.0 mA) = 53.3067.50 B; V _{WM} = 48.0 B; I _{PP} = 17.5 A	DO-214AB, SMC	х•х х•х
BFY	SMCJ51C	VISH	-	V _{BR} (I _T = 1.0 mA) = 53.3061.30 B; V _{MM} = 48.0 B; I _{pp} = 19.4 A	DO-214AB, SMC	_
		-	VS	V _{BR} (I _T = 1.0 mA) = 56.7071.80 B; V _{MM} = 51.0 B; I _{PP} = 16.5 A		X•X
BFZ	SMCJ51CA	VISH	VS	$V_{BR}(I_T = 1.0 \text{ MA}) = 56.7065.20 \text{ B}; V_{WM} = 51.0 \text{ B}; I_{pp} = 18.2 \text{ A}$	DO-214AB, SMC	X • X



Код	Типономинал	Б	Φ	Особенности	Корпус	Ц: 1•2
BG	SMBJ13CA	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 14.4016.50 \text{ B}; V_{WM} = 13.0 \text{ B}; I_{PP} = 27.9 \text{ A}$	DO-214AA, SMB	х∙х
BGD	SMCJ54C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 60.00 76.00 \text{ B}; V_{WM} = 54.0 \text{ B}; I_{PP} = 15.6 \text{ A}$	DO-214AB, SMC	x•x
BGE	SMCJ54CA	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 60.0069.00 \text{ B}; V_{WM} = 54.0 \text{ B}; I_{PP} = 17.2 \text{ A}$	DO-214AB, SMC	х∙х
BGF	SMCJ58C	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 64.4081.60 \text{ B}; V_{WM} = 58.0 \text{ B}; I_{PP} = 14.6 \text{ A}$	DO-214AB, SMC	х∙х
BGG	SMCJ58CA	VISH	νs	$V_{BR}(I_T = 1.0 \text{ mA}) = 64.4074.60 \text{ B}; V_{WM} = 58.0 \text{ B}; I_{PP} = 16.0 \text{ A}$	DO-214AB, SMC	х•х
BGH	SMCJ60C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 66.7084.50 \text{ B}; V_{WM} = 60.0 \text{ B}; I_{PP} = 14.0 \text{ A}$	DO-214AB, SMC	χ• χ
BGK	SMCJ60CA	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 66.7076.70 \text{ B}; V_{WM} = 60.0 \text{ B}; I_{PP} = 15.5 \text{ A}$	DO-214AB, SMC	х∙х
BGL	SMCJ64C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 71.1090.10 \text{ B}; V_{WM} = 64.0 \text{ B}; I_{pp} = 13.2 \text{ A}$	DO-214AB, SMC	х∙х
BGM	SMCJ64CA	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 71.1081.80 \text{ B}; V_{WM} = 64.0 \text{ B}; I_{PP} = 14.6 \text{ A}$	DO-214AB, SMC	X • X
BGN	SMCJ70C	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 77.8098.60 \text{ B}; V_{WM} = 70.0 \text{ B}; I_{PP} = 12.0 \text{ A}$	DO-214AB, SMC	х∙х
BGP	SMCJ70CA	VISH	vs	$V_{BB}(I_T = 1.0 \text{ mA}) = 77.8089.50 \text{ B}; V_{WM} = 70.0 \text{ B}; I_{PP} = 13.3 \text{ A}$	DO-214AB, SMC	х•х
BGP	TPSMA20A	GS	vs	$V_{BR}(I_T = 1.0 \text{ MA}) = 19.0021.00 \text{ B}; V_{WM} = 17.10 \text{ B}; I_{pp} = 14.4 \text{ A}$	DO-214AC, SMA	K∙A
BGQ	SMCJ75C	VISH	VS.	$V_{BR}(I_T = 1.0 \text{ mA}) = 83.30106.00 \text{ B}; V_{MM} = 75.0 \text{ B}; I_{pp} = 11.2 \text{ A}$	DO-214AB, SMC	x • x
BGR	SMCJ75CA	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 83.3095.80 \text{ B}; V_{WM} = 75.0 \text{ B}; I_{PP} = 12.4 \text{ A}$	DO-214AB, SMC	х∙х
BGS	SMCJ78C	VISH	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 86.70110.00 \text{ B}; V_{WM} = 78.0 \text{ B}; I_{pp} = 10.8 \text{ A}$	DO-214AB, SMC	х∙х
BGT	SMCJ78CA	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 86.7099.70 \text{ B}; V_{WM} = 78.0 \text{ B}; I_{PP} = 11.4 \text{ A}$	DO-214AB, SMC	χ●χ
BGU	SMCJ85C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 94.40119.20 \text{ B}; V_{WM} = 85.0 \text{ B}; I_{pp} = 9.9 \text{ A}$	DO-214AB, SMC	χ●χ
BGV	SMCJ85CA	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 94.40108.20 \text{ B}; V_{WM} = 85.0 \text{ B}; I_{PP} = 10.4 \text{ A}$	DO-214AB, SMC	х∙х
BGW	SMCJ90C	VISH	vs	$V_{BR}(I_T = 1.0 \text{ MA}) = 100.00126.50 \text{ B}; V_{WM} = 90.0 \text{ B}; I_{PP} = 9.4 \text{ A}$	DO-214AB, SMC	х∙х
BGX	SMCJ90CA	VISH	vs	$V_{BR}(I_T = 1.0 \text{ MA}) = 100.00115.50 \text{ B}; V_{WM} = 90.0 \text{ B}; I_{PP} = 10.3 \text{ A}$	DO-214AB, SMC	X • X
BGY	SMCJ100C	VISH	٧S	V _{BR} (I _T = 1.0 mA) = 111.00141.00 B; V _{WM} = 100.0 B; I _{PP} = 8.4A	DO-214AB, SMC	х∙х
BGZ	SMCJ100CA	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 111.00128.00 \text{ B}; V_{WM} = 100.0 \text{ B}; I_{pp} = 9.3 \text{ A}$	DO-214AB, SMC	х•х
BH	SMBJ14C	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 15.6019.80 \text{ B}; V_{WM} = 14.0 \text{ B}; I_{PP} = 23.3 \text{ A}$	DO-214AA, SMB	х∙х
BHD	SMCJ110C	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 122.00154.50 \text{ B}; V_{WM} = 110.0 \text{ B}; I_{pp} = 7.7 \text{ A}$	DO-214AB, SMC	x•x
BHE	SMCJ110CA	VISH	vs	V _{BR} (I _T = 1.0 mA) = 122.00140.50 B; V _{WM} = 110.0 B; I _{PP} = 8.4 A	DO-214AB, SMC	х∙х
BHF	SMCJ120C	VISH	٧S	V _{BR} (I _T = 1.0 mA) = 133.00169.00 B; V _{WM} = 120.0 B; I _{PP} = 7.0 A	DO-214AB, SMC	χ•χ
BHG	SMCJ120CA	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 133.00153.00 \text{ B}; V_{WM} = 120.0 \text{ B}; I_{pp} = 7.9 \text{ A}$	DO-214AB, SMC	χ•χ
BHH	SMCJ130C	VISH	vs	$V_{BB}(I_T = 1.0 \text{ mA}) = 144.00182.50 \text{ B}; V_{WM} = 130.0 \text{ B}; I_{PP} = 6.5 \text{ A}$	DO-214AB, SMC	х∙х
BHK	SMCJ130CA	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 144.00165.50 \text{ B}; V_{WM} = 130.0 \text{ B}; I_{PP} = 7.2 \text{ A}$	DO-214AB, SMC	X • X
BHL	SMCJ150C	VISH	٧S	$V_{BR}(I_T = 1.0 \text{ MA}) = 167.00211.50 \text{ B}; V_{WM} = 150.0 \text{ B}; I_{PP} = 5.6 \text{ A}$	DO-214AB, SMC	x•x
BHM	SMCJ150CA	VISH	٧S	V _{BR} (I _T = 1.0 mA) = 167.00192.50 B; V _{WM} = 150.0 B; I _{PP} = 6.2 A	DO-214AB, SMC	х∙х
BHN	SMCJ160C	VISH	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 178.00226.00 \text{ B}; V_{WM} = 160.0 \text{ B}; I_{pp} = 5.2 \text{ A}$	DO-214AB, SMC	х∙х
BHP	SMCJ160CA	VISH	VS	V _{BR} (I _T = 1.0 mA) = 178.00205.00 B; V _{WM} = 160.0 B; I _{PP} = 5.8 A	DO-214AB, SMC	х∙х
BHP	TPSMA22	GS	νs	$V_{BR}(I_T = 1.0 \text{ mA}) = 19.8024.20 \text{ B}; V_{WM} = 17.80 \text{ B}; I_{pp} = 12.5 \text{ A}$	DO-214AC, SMA	K•A
BHQ	SMCJ170C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 189.00239.50 \text{ B}; V_{WM} = 170.0 \text{ B}; I_{PP} = 4.9 \text{ A}$	DO-214AB, SMC	χ●χ
BHR	SMCJ170CA	VISH	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 189.00217.50 \text{ B}; V_{WM} = 170.0 \text{ B}; I_{pp} = 5.5 \text{ A}$	DO-214AB, SMC	x•x
BK	SMBJ14CA	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 15.6017.90 \text{ B}; V_{WM} = 14.0 \text{ B}; I_{pp} = 25.8 \text{ A}$	DO-214AA, SMB	х∙х
BKP	TPSMA22A	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 20.9023.10 \text{ B}; V_{WM} = 18.80 \text{ B}; I_{pp} = 13.1 \text{ A}$	DO-214AC, SMA	K•A
BL	SMBJ15C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 16.7021.10 \text{ B}; V_{WM} = 15.0 \text{ B}; I_{pp} = 22.3 \text{ A}$	DO-214AA, SMB	х∙х
BLP	TPSMA24	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 21.6026.40 \text{ B}; V_{WM} = 19.40 \text{ B}; I_{PP} = 11.5 \text{ A}$	DO-214AC, SMA	K•A
BM	SMBJ15CA	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 16.7019.20 \text{ B}; V_{WM} = 15.0 \text{ B}; I_{PP} = 24.0 \text{ A}$	DO-214AA, SMB	х∙х
BMP	TPSMA24A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 22.8025.20 \text{ B}; V_{WM} = 20.50 \text{ B}; I_{pp} = 12.0 \text{ A}$	DO-214AC, SMA	K•A
BN	SMBJ16C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 17.8022.60 \text{ B}; V_{WM} = 16.0 \text{ B}; I_{pp} = 20.8 \text{ A}$	DO-214AA, SMB	х∙х
BNP	TPSMA27	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 24.3029.70 \text{ B}; V_{WM} = 21.80 \text{ B}; I_{pp} = 10.2 \text{ A}$	DO-214AC, SMA	K•A
BOP	TPSMA30	GS	vs	V _{BR} (I _T = 1.0 mA) = 27.0033.00 B; V _{WM} = 24.30 B; I _{PP} = 9.2 A	DO-214AC, SMA	K•A
BP	SMBJ16CA	VISH	vs	V _{BR} (I _T = 1.0 mA) = 17.8020.50 B; V _{WM} = 16.0 B; I _{PP} = 23.1 A	DO-214AA, SMB	χ●χ
BPP	TPSMA27A	GS	٧S	V _{BR} (I _T = 1.0 mA) = 25.7028.40 B; V _{VM} = 23.10 B; I _{PP} = 10.7 A	DO-214AC, SMA	K•A
BQ	SMBJ17C	VISH	vs	V _{BR} (I _T = 1.0 mA) = 18.9023.90 B; V _{WM} = 17.0 B; I _{PP} = 19.7 A	DO-214AA, SMB	х∙х
BR	SMBJ17CA	VISH	vs	V _{BR} (I _T = 1.0 mA) = 18.9021.70 B; V _{WM} = 17.0 B; I _{PP} = 21.7 A	DO-214AA, SMB	х∙х
BRP	TPSMA30A	GS	٧S	V _{BR} (I _T = 1.0 mA) = 28.5031.50 B; V _{WM} = 25.60 B; I _{PP} = 9.7 A	DO-214AC, SMA	K•A
BS	SMBJ18C	VISH	vs	V _{BR} (I _T = 1.0 mA) = 20.0025.30 B; V _{WM} = 18.0 B; I _{PP} = 18.6 A	DO-214AA, SMB	х∙х
BSP	TPSMA33	GS	vs	V _{BR} (I _T = 1.0 mA) = 29.7036.30 B; V _{WM} = 26.80 B; I _{PP} = 8.4 A	DO-214AC, SMA	K•A
BT	SMBJ18CA	VISH	vs	V _{BR} (I _T = 1.0 mA) = 20.0023.30 B; V _{WM} = 18.0 B; I _{PP} = 20.5 A	DO-214AA, SMB	х∙х





Код	Типономинал	Б	Φ	Особенности	Корпус	Ц: 1•2
BTP	TPSMA33A	GS	٧S	V _{BR} (I _T = 1.0 mA) = 31.4034.70 B; V _{MM} = 28.20 B; I _{PP} = 8.8 A	DO-214AC, SMA	K∙A
BU	SMBJ20C	VISH	VS	V _{BR} (I _T = 1.0 mA) = 22.2028.10 B; V _{MM} = 20.0B; I _{PP} = 16.7 A	DO-214AA, SMB	х∙х
BUP	TPSMA36	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 32.4039.60 \text{ B}; V_{MM} = 29.10 \text{ B}; I_{PP} = 7.7 \text{ A}$	DO-214AC, SMA	K•A
BV	SMBJ20CA	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 22.2025.50 \text{ B}; V_{WM} = 20.0 \text{ B}; I_{PP} = 18.5 \text{ A}$	DO-214AA, SMB	х∙х
BVP	TPSMA36A	GS	VS	V _{BR} (I _T = 1.0 mA) = 34.2037.80 B; V _{WM} = 30.80 B; I _{PP} = 8.0 A	DO-214AC, SMA	K•A
BW	SMBJ22C	VISH	VS	V _{BR} (I _T = 1.0 mA) = 24.4030.90 B; V _{WM} = 22.0 B; I _{PP} = 15.2 A	DO-214AA, SMB	х∙х
BWP	TPSMA39	GS	VS	V _{BR} (I _T = 1.0 mA) = 35.1042.90 B; V _{WM} = 31.60 B; I _{PP} = 7.1 A	DO-214AC, SMA	K•A
ВХ	SMBJ22CA	VISH	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 24.4028.00 \text{ B}; V_{WM} = 22.0 \text{ B}; I_{PP} = 16.9 \text{ A}$	DO-214AA, SMB	х∙х
BXP	TPSMA39A	GS	VS	V _{BR} (I _T = 1.0 mA) = 37.1041.00 B; V _{MM} = 33.30 B; I _{PP} = 7.4 A	DO-214AC, SMA	K•A
BY	SMBJ24C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 26.7033.80 \text{ B}; V_{MM} = 24.0 \text{ B}; I_{PP} = 14.0 \text{ A}$	DO-214AA, SMB	х∙х
BYP	TPSMA43	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 38.7047.30 \text{ B}; V_{MM} = 34.80 \text{ B}; I_{PP} = 6.5 \text{ A}$	DO-214AC, SMA	K•A
BZ	SMBJ24AC	VISH	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 26.7030.70 \text{ B}; V_{WM} = 24.0 \text{ B}; I_{PP} = 15.4 \text{ A}$	DO-214AA, SMB	х∙х
BZP	TPSMA43A	GS	VS	V _{BB} (I _T = 1.0 mA) = 40.9045.20 B; V _{MM} = 36.80 B; I _{PP} = 6.7 A	DO-214AC, SMA	K•A
C2	SMBYT03-200	STM	frd	$V_B < 200 \text{ B}; I_F < 3 \text{ A}; V_F (I_F = 3 \text{ A}) < 1.4 \text{ B}; I_B < 0.6 \text{ mA}; t_{BB} < 60 \text{ HC}$	DO-214AB, SMC	K•A
C3	SMBYT03-300	STM	frd	$V_B < 300 \text{ B}; I_E < 3 \text{ A}; V_E (I_E = 3 \text{ A}) < 1.4 \text{ B}; I_B < 0.6 \text{ mA}; t_{BB} < 60 \text{ Hz}$	DO-214AB, SMC	K•A
C4	SMBYT03-400	STM	frd	V _B < 400 B; I _F < 3 A; V _F (I _F = 3 A) < 1.4 B; I _B < 0.6 mA; t _{BB} < 60 HC	DO-214AB, SMC	K•A
CD	SMBJ26C	VISH	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 28.9036.80 \text{ B}; V_{WM} = 26.0 \text{ B}; I_{PP} = 12.4 \text{ A}$	DO-214AA, SMB	χ●χ
CE	SMBJ26CA	VISH	VS	V _{BR} (I _T = 1.0 mA) = 28.9033.20 B; V _{WM} = 26.0 B; I _{PP} = 14.2 A	DO-214AA, SMB	х∙х
CF	SMBJ28C	VISH	VS	V _{BB} (I _T = 1.0 mA) = 31.1039.40 B; V _{MM} = 28.0 B; I _{PP} = 12.0 A	DO-214AA, SMB	x•x
CG	SMBJ28CA	VISH	VS	V _{BB} (I _T = 1.0 mA) = 31.1035.80 B; V _{MM} = 28.0 B; I _{PP} = 13.2 A	DO-214AA, SMB	х∙х
СН	SMB30C	VISH	vs	V _{BB} (I _T = 1.0 mA) = 33.3042.20 B; V _{MM} = 30.0 B; I _{PP} = 11.2 A	DO-214AC, SMA	х∙х
СК	SMBJ30CA	VISH	VS	V _{BB} (I _T = 1.0 mA) = 33.3038.30 B; V _{MM} = 30.0B; I _{PP} = 12.4 A	DO-214AA, SMB	х∙х
CL	SMBJ33C	VISH	vs	V _{BR} (I _T = 1.0 MA) = 36.7046.90 B; V _{WM} = 33.0 B; I _{PP} = 10.2 A	DO-214AA SMB	х∙х
CM	SMBJ33CA	VISH	vs	V _{BR} (I _T = 1.0 MA) = 36.7042.20 B; V _{WM} = 33.0 B; I _{PP} = 11.3 A	DO-214AA, SMB	x•x
CN	SMBJ36C	VISH	vs	V _{BB} (I _T = 1.0 MA) = 40.0050.70 B; V _{MM} = 36.0 B; I _{PP} = 9.3 A	DO-214AA SMB	х•х
CP	SMBJ36CA	VISH	vs	V _{BB} (I _T = 1.0 MA) = 40.0046.00 B; V _{MM} = 36.0 B; I _{PP} = 10.3 A	DO-214AA SMB	x•x
CQ	SMBJ40C	VISH	VS	V _{BB} (I _T = 1.0 MA) = 44.4056.30 B; V _{WM} = 40.0B; I _{PP} = 8.4A	DO-214AA, SMB	x•x
CR	SMBJ40CA	VISH	vs	V _{BB} (I _T = 1.0 MA) = 44.4051.10 B; V _{WM} = 40.0 B; I _{PP} = 9.3 A	DO-214AA, SMB	x•x
CS	SMBJ43C	VISH	vs	V _{BB} (I _T = 1.0 MA) = 47.8060.50 B; V _{WM} = 43.0B; I _{PP} = 7.8A	DO-214AA, SMB	x•x
СТ	SMBJ43CA	VISH	VS	V _{BB} (I _T = 1.0 MA) = 47.8054.90 B; V _{MM} = 43.0 B; I _{PP} = 8.6 A	DO-214AA, SMB	x•x
CU	SMBJ45C	VISH	vs	V _{BB} (I _T = 1.0 MA) = 50.0063.30 B; V _{MM} = 45.0B; I _{PP} = 7.5A	DO-214AA SMB	x•x
CV	SMBJ45CA	VISH	vs	V _{BB} (I _T = 1.0 MA) = 50.0057.50 B; V _{MM} = 45.0 B; I _{PP} = 8.3 A	DO-214AA SMB	x•x
CW	SMBJ48C	VISH	VS	V _{BB} (I _T = 1.0 MA) = 53.3067.50 B; V _{MM} = 48.0 B; I _{PP} = 7.0 A	DO-214AA SMB	x•x
cx	SMBJ48CA	VISH	vs	V _{BB} (I _T = 1.0 MA) = 53.3061.30 B; V _{WM} = 48.0 B; I _{PP} = 7.7 A	DO-214AA, SMB	X•X
CY	SMBJ51C	VISH	VS	V _{BR} (I _T = 1.0 MA) = 56.7071.80 B; V _{MM} = 51.0 B; I _{PP} = 6.6 A	DO-214AA, SMB	x•x
CZ	SMBJ51CA	VISH	VS	V _{BB} (I _T = 1.0 MA) = 56.7065.20 B; V _{MM} = 51.0B; I _{DD} = 7.3A	DO-214AA, SMB	X • X
D20	SMBYW04-200	STM	frd	V _B < 200 B; I _F < 4A; V _F (I _F = 4A) < 0.85 B; I _B < 0.5 mA; t _{BB} < 35 Hc	DO-214AB, SMC	K•A
DD	SMBJ54C	VISH	VS.	V _{BB} (I _T = 1.0 mA) = 60.0076.00 B; V _{MM} = 54.0B; I _{DD} = 6.2A	DO-214AA, SMB	X•X
DDP	TPSMC6.8	GS	VS	V _{BR} (I _T = 10.0 mA) = 6.127.48 B; V _{WM} = 5.50 B; I _{PP} = 139A	DO-214AB, SMC	K•A
DE	SMBJ54CA	VISH	VS	V _{BB} (I _T = 1.0 MA) = 60.0069.00 B; V _{WM} = 54.0B; I _{PP} = 6.9A	DO-214AA, SMB	X•X
DEP	TPSMC6.8A	GS	VS	V _{BR} (I _T = 10.0 mA) = 6.457.14B; V _{WM} = 5.80 B; I _{PP} = 143A	DO-214AB, SMC	K•A
DE	SMBJ58C	VISH	VS	V _{BR} (I _T = 1.0 MA) = 64.4081.60 B; V _{WM} = 58.0B; I _{PP} = 5.8A	DO-214AA, SMB	X•X
DFP	TPSMC7.5	GS	VS VS	V _{BB} (I _T = 10.0 MA) = 6.758.25B; V _{WM} = 6.05B; I _{PP} = 128A	DO-214AB, SMC	K•A
DG	SMBJ58CA	VISH	VS VS	V _{BB} (I _T = 1.0 MA) = 64.4074.60 B; V _{MM} = 58.0 B; I _{pp} = 120 A	DO-214AA, SMB	X•X
DGP	TPSMC7.5A	GS	VS VS		DO-214AB, SMC	K•A
DH	SMBJ60C	VISH	VS VS	$V_{BR}(I_1 = 10.0 \text{ mA}) = 7.137.88 \text{ B}; V_{WM} = 6.40 \text{ B}; I_{PP} = 133 \text{ A}$ $V_{BR}(I_1 = 1.0 \text{ mA}) = 66.7084.50 \text{ B}; V_{WM} = 60.0 \text{ B}; I_{PP} = 5.6 \text{ A}$	DO-214AA, SMB	X=X
DHP	TPSMC8.2	GS	VS VS	1. The state of th	DC-214AB, SMC	K•A
DK	SMBJ60CA	VISH	VS VS	$V_{BR}(I_T = 10.0 \text{ MA}) = 7.389.02 \text{ B; } V_{WM} = 6.63 \text{ B; } I_{PP} = 120 \text{ A}$ $V_{BR}(I_T = 1.0 \text{ MA}) = 66.7076.70 \text{ B; } V_{WM} = 60.08 \text{ I}_{PP} = 6.2 \text{ A}$	DO-214AB, SMC DO-214AA, SMB	X=X
DKP	TPSMC8.2A	GS			DO-214AB, SMC	K•A
DL	SMBJ64C	VISH	VS vc	V _{BR} (I _T = 10.0 mA) = 7.798.61B; V _{WM} = 7.02 B; I _{PP} = 124A	DO-214AB, SMC DO-214AA, SMB	X•X
DLP	TPSMC9.1	GS	vs vs	V _{BR} (I _T = 1.0 mA) = 71.1090.10 B; V _{MM} = 64.0B; I _{PP} = 5.3A	DO-214AA, SMB DO-214AB, SMC	X•X K•A
DM	SMBJ64CA	VISH		V _{BR} (I _T = 1.0 mA) = 8.1910.0B; V _{WM} = 7.37 B; I _{PP} = 109 A	DO-214AB, SMC	
100,000	22.2353.253.253.25		VS	V _{BR} (I _T = 1.0 mA) = 71.1081.80 B; V _{MM} = 64.0B; I _{PP} = 5.8A		X•X
DMP	TPSMC9.1A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 8.659.55B; V_{WM} = 7.78B; I_{pp} = 112A$	DO-214AB SMC	K•A



Код	Типономинал	Б	Φ	Особенности	Корпус	Ц: 1•2
DN	SMBJ70C	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 77.8098.60 \text{ B}; V_{WM} = 70.0 \text{ B}; I_{PP} = 4.8 \text{ A}$	DO-214AA, SMB	x•x
DNP	TPSMC10	GS	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 9.0011.0 \text{ B}; V_{WM} = 8.10 \text{ B}; I_{pp} = 100 \text{ A}$	DO-214AB, SMC	K•A
DOP	TPSMC11	GS	vs	$V_{BR}(I_T = 1.0 \text{ MA}) = 9.9012.1 \text{ B}; V_{WM} = 8.92 \text{ B}; I_{PP} = 92.6 \text{ A}$	DO-214AB, SMC	K•A
DP	SMBJ70CA	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 77.8089.50 \text{ B}; V_{VM} = 70.0 \text{ B}; I_{PP} = 5.3 \text{ A}$	DO-214AA, SMB	х∙х
DPP	TPSMC10A	GS	νs	$V_{BR}(I_T = 1.0 \text{ mA}) = 9.5010.5 \text{ B}; V_{WM} = 8.55 \text{ B}; I_{pp} = 103 \text{ A}$	DO-214AB, SMC	K∙A
DQ	SMBJ75C	VISH	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 83.30106.00 \text{ B}; V_{WM} = 75.0 \text{ B}; I_{PP} = 4.5 \text{ A}$	DO-214AA, SMB	х∙х
DR	SMBJ75CA	VISH	vs	V _{BR} (I _T = 1.0 mA) = 83.3095.80 B; V _{WM} = 75.0 B; I _{PP} = 4.9 A	DO-214AA, SMB	х∙х
DRP	TPSMC11A	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 10.511.6B; V_{WM} = 9.40B; I_{PP} = 96.2A$	DO-214AB, SMC	K∙A
DS	SMBJ78C	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 86.70110.00 \text{ B}; V_{WM} = 78.0 \text{ B}; I_{pp} = 4.3 \text{ A}$	DO-214AA, SMB	x•x
DSP	TPSMC12	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 10.813.2 \text{ B}; V_{WM} = 9.72 \text{ B}; I_{pp} = 86.7 \text{ A}$	DO-214AB, SMC	K•A
DT	SMBJ78CA	VISH	vs	V _{BR} (I _T = 1.0 mA) = 86.7099.70 B; V _{WM} = 78.0 B; I _{PP} = 4.7 A	DO-214AA, SMB	х∙х
DTP	TPSMC12A	GS	vs	$V_{BB}(I_T = 1.0 \text{ mA}) = 11.412.6 \text{ B}; V_{WM} = 10.2 \text{ B}; I_{pp} = 89.8 \text{ A}$	DO-214AB, SMC	K•A
DU	SMBJ85C	VISH	VS.	$V_{BB}(I_T = 1.0 \text{ mA}) = 94.40119.20 \text{ B}; V_{WM} = 85.0 \text{ B}; I_{pp} = 3.9 \text{ A}$	DO-214AA, SMB	х∙х
DUP	TPSMC13	GS	vs	V _{BB} (I _T = 1.0 mA) = 11.714.3 B; V _{WM} = 10.5 B; I _{PP} = 78.9 A	DO-214AB, SMC	K•A
DV	SMBJ85CA	VISH	vs	$V_{BB}(I_T = 1.0 \text{ mA}) = 94.40108.20 \text{ B}; V_{WM} = 85.0 \text{ B}; I_{PP} = 4.4 \text{ A}$	DO-214AA, SMB	х∙х
DVP	TPSMC13A	GS	vs	V _{BR} (I _T = 1.0 mA) = 12.413.7B; V _{WM} = 11.1B; I _{PP} = 82.4A	DO-214AB, SMC	K•A
D₩	SMBJ90C	VISH	vs	V _{BR} (I _T = 1.0 mA) = 100.0126.50 B; V _{WM} = 90.0 B; I _{PP} = 3.8 A	DO-214AA, SMB	x•x
DWP	TPSMC15	GS	vs	V _{BB} (I _T = 1.0 mA) = 13.516.5 B; V _{WM} = 12.1 B; I _{PP} = 68.2 A	DO-214AB, SMC	K•A
DX	SMBJ90CA	VISH	vs	V _{BB} (I _T = 1.0 mA) = 100.0115.50 B; V _{WM} = 90.0 B; I _{PP} = 4.1 A	DO-214AA, SMB	x•x
DXP	TPSMC15A	GS	vs	V _{BB} (I _T = 1.0 mA) = 14.315.8B; V _{MM} = 12.8B; I _{pp} = 70.8A	DO-214AB, SMC	K•A
DY	SMBJ100C	VISH	vs	V _{BB} (I _T = 1.0 mA) = 111.0141.00 B; V _{WM} = 100.0 B; I _{PP} = 3.4 A	DO-214AA, SMB	x•x
DYP	TPSMC16	GS	vs	V _{BB} (I _T = 1.0 mA) = 14.417.6B; V _{MM} = 12.9B; I _{pp} = 63.8A	DO-214AB, SMC	K•A
DZ	SMBJ100CA	VISH	vs	V _{BR} (I _T = 1.0 mA) = 111.0128.00 B; V _{WM} = 100.0 B; I _{PP} = 3.7 A	DO-214AA, SMB	х•х
DZP	TPSMC16A	GS	vs	V _{RR} (I _T = 1.0 mA) = 15.216.8 B; V _{MM} = 13.6 B; I _{DP} = 66.7 A	DO-214AB, SMC	K•A
EA	ES1A	GS	fd	V _R =50 B; I _ε =1 A; C _D =7 nΦ	DO-214AC, SMA	K•A
EA	ES2A	GS	fd	V _B = 50 B; I _E = 2 A; C _D = 18 пФ	DO-214AA, SMB	K•A
EA	ES3A	GS	fd	V _B = 50 B; I _E = 3 A; C _D = 45 пФ	DO-214AB, SMC	K•A
EB	ES1B	GS	fd	V _B = 100 B; I _E = 1 A; C _D = 7 n Φ	DO-214AC, SMA	K•A
EB	ES2B	GS	fd	V _B = 100 B; I _E = 2 A; C _D = 18 πΦ	DO-214AA, SMB	K•A
EB	ES3B	GS	fd	V _B = 100 B; I _F = 3 A; C _D = 45 nΦ	DO-214AB, SMC	K•A
EC	ES1C	GS	fd	V _B = 150 B; I _E = 1 A; C _D = 7 nΦ	DO-214AC, SMA	K•A
EC	ES2C	GS	fd	V _B = 150 B; I _E = 2 A; C _D = 18 nΦ	DO-214AA, SMB	K•A
EC	ES3C	GS	fd	V _B = 150 B; I _E = 3 A; C _D = 45 nΦ	DO-214AB, SMC	K•A
ED	ES1D	GS	fd	V _B = 200 B; I _E = 1 A; C _D = 7 πΦ	DO-214AC, SMA	K•A
ED	ES2D	GS	fd	V _B = 200 B; I _F = 1 A; C _D = 7 N Φ	DO-214AA, SMB	K•A
ED	ES3D	GS	fd	V _B = 200 B; I _F = 3 A; C _D = 16 HΦ	DO-214AB, SMC	K•A
ED	SMBJ110C	VISH	vs.	V _{RR} = 200 B, I _F = 3 A, G _D = 45 II D V _{RR} (I _T = 1.0 MA) = 122.0154.50 B; V _{MM} = 110.0 B; I _{PP} = 3.0 A	DO-214AA, SMB	X•X
FDP	TPSMC18	GS	_		DO-214AB, SMC	K•A
EE	SMBJ110CA	VISH	vs	V _{BR} (I _T = 1.0 mA) = 16.219.8 B; V _{WM} = 14.5 B; I _{pp} = 56.6 A		100
EEP			vs	V _{BR} (I _T = 1.0 MA) = 122.0140.00 B; V _{MM} = 110.0 B; I _{PP} = 3.4 A	DO-214AA, SMB	X • X
	TPSMC18A	GS	VS	V _{BH} (I _T = 1.0 mA) = 17.118.9B; V _{WM} = 15.3B; I _{PP} = 59.5A	DO-214AB, SMC	K•A
EF	SMBJ120C	VISH	VS	V _{BR} (I _T = 10 mA) = 133.0169.00 B; V _{WM} = 120.0 B; I _{PP} = 2.8 A	DO-214AA, SMB	χ•χ
EFP	TPSMC20	GS	VS	V _{BR} (I _T = 1.0 mA) = 18.022.0B; V _{WM} = 16.2B; I _{pp} = 51.5A	DO-214AB, SMC	K•A
EG	SMBJ120CA	VISH	VS	V _{BR} (I _T = 1.0 mA) = 133.0153.00 B; V _{MM} = 120.0 B; I _{PP} = 3.1 A	DO-214AA, SMB	χ•χ
EGP	TPSMC20A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 19.021.0 \text{ B}; V_{WM} = 17.1 \text{ B}; I_{pp} = 54.2 \text{ A}$	DO-214AB, SMC	K∙A
EH	SMBJ130C	VISH	VS	V _{BR} (I _T = 1.0 mA) = 144.0182.50 B; V _{WM} = 130.0 B; I _{PP} = 2.6 A	DO-214AA, SMB	х∙х
EHP	TPSMC22	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 19.824.2 \text{ B}; V_{WM} = 17.8 \text{ B}; I_{PP} = 47.0 \text{ A}$	DO-214AB, SMC	K•A
EK	SMBJ130CA	VISH	VS	V _{BR} (I _T = 1.0 mA) = 144.0165.50 B; V _{WM} = 130.0 B; I _{PP} = 2.9 A	DO-214AA, SMB	X • X
EKP	TPSMC22A	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 20.923.1 \text{ B}; V_{WM} = 18.8 \text{ B}; I_{PP} = 49.0 \text{ A}$	DO-214AB, SMC	K∙A
EL	SMBJ150C	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 167.0211.50 \text{ B}; V_{WM} = 150.0 \text{ B}; I_{PP} = 2.2 \text{ A}$	DO-214AA, SMB	х∙х
ELP	TPSMC24	GS	νs	V _{BR} (I _T = 1.0 mA) = 21.626.4B; V _{WM} = 19.4B; I _{PP} = 43.2A	DO-214AB, SMC	K•A
EM	SMBJ150CA	VISH	νs	$V_{BR}(I_T = 1.0 \text{ mA}) = 167.0192.50 \text{ B}; V_{WM} = 150.0 \text{ B}; I_{PP} = 2.5 \text{ A}$	DO-214AA, SMB	х∙х
EMP	TPSMC24A	GS	vs	V _{BR} (I _T = 1.0 mA) = 22.825.2B; V _{WM} = 20.5B; I _{PP} = 45.2A	DO-214AB, SMC	K∙A
EN	SMBJ160C	VISH	vs	V _{BR} (I _T = 1.0 mA) = 178.0226.00 B; V _{WM} = 160.0 B; I _{PP} = 2.1 A	DO-214AA, SMB	х∙х





EP PROMICE/TA SS US V _{(Ep} (t) = 1.0 mA) = 178.0. 226 0.0 B, V _{(Ep} = 160.0 B, t _{Ep} = 2.3 A DC. 214AA, SMB V _{EP} AB C SMB, SMB, TOC V VISH V _{EP} V _{EP} (t) = 1.0 mA) = 178.0. 226 0.0 B, V _{EP} = 170.0 B, t _{Ep} = 2.0 A DC. 214AB, SMC K=A DC. 214AB, SMC V _{EP} V _{EP} = 170.0 B, t _{Ep} = 2.0 A DC. 214AB, SMC K=A DC. 214AB, SMC K=A SMB, V _{EP} V _{EP} V _{EP} SMB, V _{EP} V	Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2
EPP TPSMC33A SS vs V _{gst} (t ₁ = 1 0 uAs) = 25.7 . 28.4 E; V _{gst} (± = 1 0 uAs) = 25.7 . 28.4 E; V _{gst} = 23.1 E; t _{tp} = 40.0 A	ENP	TPSMC27	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 24.329.7 \text{B}; V_{WM} = 21.8 \text{B}; I_{PP} = 38.4 \text{A}$	DO-214AB, SMC	K•A
EQ	EP	SMBJ160CA	VISH	VS	V _{BR} (I _T = 1.0 mA) = 178.0205.00 B; V _{WM} = 160.0 B; I _{PP} = 2.3 A	DO-214AA, SMB	х∙х
EGP TPSMC30 GS vs Vgs(t) = 1 0 uAb) = 27 0. 33 GB, Vgs_t = 24 3B, t_p = 34.5A DC 214AB, SMC v= A SMB.770C AVS visit vs Vgs(t) = 1 0 uAb) = 189 0. 217 5GB, Vgs_t = 71 0 DB, t_s = 22 A DC 214AB, SMC v= A SPP TPSMC30A GS vs Vgs(t) = 1 0 uAb) = 28 0. 15 By, vs_t = 25 BB, t_p = 36 2A DC 214AB, SMC v= A SPP TPSMC30A GS vs Vgs(t) = 1 0 uAb) = 22 A. 36 By, vs_t = 26 BB, t_p = 36 2A DC 214AB, SMC v= A SPP TPSMC30A GS vs Vgs(t) = 1 0 uAb) = 22 A. 36 By, vs_t = 26 BB, t_p = 36 A DC 214AB, SMC v= A SPP TPSMC30B GS vs Vgs(t) = 1 0 uAb) = 22 A. 39 BB, vs_t = 26 BB, t_p = 32 BA DC 214AB, SMC v= A SPP TPSMC30B GS vs Vgs(t) = 1 0 uAb) = 32 A. 39 BB, vs_t = 30 BB, t_p = 30 IA DC 214AB, SMC v= A SPP TPSMC30B GS vs Vgs(t) = 1 0 uAb) = 32 A. 39 BB, vs_t = 30 BB, t_p = 26 BA DC 214AB, SMC v= A SPP TPSMC30B GS vs Vgs(t) = 1 0 uAb) = 32 A. 39 BB, vs_t = 30 BB, t_p = 26 BA DC 214AB, SMC v= A SPP TPSMC30B GS vs Vgs(t) = 1 0 uAb) = 32 A. 37 BB, Vs_t = 30 BB, t_p = 26 BA DC 214AB, SMC v= A SPP TPSMC30B GS vs Vgs(t) = 1 0 uAb) = 32 A. 37 BB, Vs_t = 30 BB, t_p = 26 BA DC 214AB, SMC v= A SPP TPSMC30B GS vs Vgs(t) = 1 0 uAb) = 32 A. 37 BB, Vs_t = 34 BB, t_p = 26 BA DC 214AB, SMC v= A SPP TPSMC30B GS vs Vgs(t) = 10 uAb) = 32 A. 37 BB, Vs_t = 34 BB, t_p = 26 AA DC 214AB, SMC v= A SPP TPSMC30B GS vs Vgs(t) = 10 uAb) = 32 A. 37 BB, Vs_t = 34 BB, t_p = 26 AA DC 214AB, SMC v= A SPP TPSMC30B GS vs Vgs(t) = 10 uAb) = 32 A. 37 BB, Vs_t = 34 BB, t_p = 25 AA DC 214AB, SMC v= A SPR tPSM SMC sA SPR tPSM S	EPP	TPSMC27A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 25.728.4 \text{ B}; V_{WM} = 23.1 \text{ B}; I_{pp} = 40.0 \text{ A}$	DO-214AB, SMC	K•A
## SMBJ170CA VISH VS V _{SR} (H=1 0 MA)=189.0.217.50 B, V _{MA} =170.0 B, I _{MO} =2.2 A ## DO-214AB, SMC K=A ## DO-21	EQ	SMBJ170C	VISH	VS	V _{BR} (I _T = 1.0 mA) = 189.0239.50 B; V _{WM} = 170.0 B; I _{PP} = 2.0 A	DO-214AA, SMB	х∙х
EPP TPSMC39A SS vs V _{BR} (t = 1 0 aab) = 28.5. 31 5B, V _{BB} = 25 8B, I _{BP} = 36.2A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 29.7. 36.3B, V _{BB} = 28.8B, I _{BP} = 31.4A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 24.7. 36.3B, V _{BB} = 28.8B, I _{BP} = 31.4A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 24.4B, SMC × A V _{BR} (t = 1 0 aab) = 24.4B, SMC × A V _{BR} (t = 1 0 aab) = 24.4B, SMC × A V _{BR} (t = 1 0 aab) = 24.4B, SMC × A V _{BR} (t = 1 0 aab) = 24.4B, SMC × A V _{BR} (t = 1 0 aab) = 24.4B, SMC × A V _{BR} (t = 1 0 aab) = 25.1.4 2.8B, V _{BB} = 30.8B, I _{BP} = 30.1A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 25.1.4 2.8B, V _{BB} = 36.8B, I _{BP} = 36.6A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 25.1.4 2.8B, V _{BB} = 36.8B, I _{BP} = 26.6A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 35.1.4 2.8B, V _{BB} = 33.8B, I _{BP} = 27.8A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 35.1.4 2.8B, V _{BB} = 33.8B, I _{BP} = 27.8A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 30.8.74, 73.8B, V _{BB} = 36.8B, I _{BP} = 25.6A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 30.8.74, 73.8B, V _{BB} = 36.8B, I _{BP} = 25.6A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 30.8.74, 73.8B, V _{BB} = 36.8B, I _{BP} = 25.6A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 30.8.74, 73.8B, V _{BB} = 36.8B, I _{BP} = 25.6A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 30.8.74, 73.8B, V _{BB} = 36.8B, I _{BP} = 25.6A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 30.8.74, 73.8B, V _{BB} = 36.8B, I _{BP} = 39.4A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 30.85, 73.8B, I _{BP} = 25.8A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 30.85, 73.8B, I _{BP} = 25.8B, I _{BP} = 104.2A DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 30.8B, I _{BP} = 30.8B, I _{BP} = 30.0 DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 30.8B, I _{BP} = 30.0 DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 30.8B, I _{BP} = 30.8B, I _{BP} = 30.0 DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 30.8B, I _{BP} = 30.8B, I _{BP} = 30.0 DO-2144B, SMC × A V _{BR} (t = 1 0 aab) = 30.8B, I _{BP} = 30.8B, I _{BP}	EQP	TPSMC30	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 27.033.0 \text{B}; V_{WM} = 24.3 \text{B}; I_{pp} = 34.5 \text{A}$	DO-214AB, SMC	K•A
ESP TPSMC333 GS vs V _{RR} (t+ = 1 0 мA) = 29.736.3B; V _{WW} = 26.8B; t _p = 31.4A DO-214AB; SMC K+A ETP TPSMC33A GS vs V _{RR} (t+ = 1 0 mA) = 2439.2B; V _{WW} = 26.8B; t _p = 32.8A DO-214AB; SMC K+A EVP TPSMC36 GS vs V _{RR} (t+ = 1 0 mA) = 2439.2B; V _{WW} = 29.8B; t _p = 20.8B DO-214AB; SMC K+A EVP TPSMC36 GS vs V _{RR} (t+ = 1 0 mA) = 2439.2B; V _{WW} = 30.8B; t _p = 30.1A DO-214AB; SMC K+A EVP TPSMC39 GS vs V _{RR} (t+ = 1 0 mA) = 3714.1B; t _p = 26.6A DO-214AB; SMC K+A EVP TPSMC39 GS vs V _{RR} (t+ = 1 0 mA) = 3714.1B; t _p = 26.6A DO-214AB; SMC K+A EVP TPSMC39 GS vs V _{RR} (t+ = 1 0 mA) = 3714.1B; t _p = 30.8B; t _p = 26.6A DO-214AB; SMC K+A EVP TPSMC33 GS vs V _{RR} (t+ = 1 0 mA) = 3714.1B; t _p = 24.2A DO-214AB; SMC K+A EVP TPSMC43 GS vs V _{RR} (t+ = 1 0 mA) = 3714.1B; t _p = 24.2A DO-214AB; SMC K+A EVP TPSMC43 GS vs V _{RR} (t+ = 1 0 mA) = 3714.1B; t _p = 24.2A DO-214AB; SMC K+A EVP TPSMC43 GS vs V _{RR} (t+ = 1 0 mA) = 3714.1B; t _p = 24.2A DO-214AB; SMC K+A EVP TPSMC43 GS vs V _{RR} (t+ = 1 0 mA) = 3714.1B; t _p = 24.2A DO-214AB; SMC x+X EVP TPSMC43 GS vs V _{RR} (t+ = 1 0 mA) = 3712B; t _p = 38.8B; t _p = 25.6A DO-214AB; SMC x+X EVP TPSMC43 GS vs V _{RR} (t+ = 1 0 mA) = 3712B; t _p = 38.8 t _p = 25.6A DO-214AB; SMC x+X EVP TPSMC43 GS vs V _{RR} (t+ = 1 0 mA) = 3712B; t _p = 38.8 t _p = 25.6A DO-214AB; SMC x+X EVR SMC165CA STM vs V _{RR} (t+ = 1 0 mA) = 3712B; t _p = 38.8 t _p = 25.6A DO-214AB; SMC x+X EVR SMC165CA STM vs V _{RR} (t+ = 1 0 mA) = 3712B; t _p = 10.8 t _p = 163.0A DO-214AB; SMC x+X EVR SMC165CA STM vs V _{RR} (t+ = 1 0 mA) = 13.3016.90B; t _{pm} = 163.0A DO-214AB; SMC x+X EVR SMC165CA STM vs V _{RR} (t+ = 1 0 mA) = 33.3016.90B; t _{pm} = 163.0A DO-214AB; SMC x+X EVR SMC165CA STM vs V _{RR} (t+ = 1 0 mA) = 33.3016.90B; t _{pm}	ER	SMBJ170CA	VISH	VS	V _{BR} (I _T = 1.0 mA) = 189.0217.50 B; V _{WM} = 170.0 B; I _{PP} = 2.2 A	DO-214AA, SMB	х∙х
ETP	ERP	TPSMC30A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 28.531.5 \text{ B}; V_{WM} = 25.6 \text{ B}; I_{PP} = 36.2 \text{ A}$	DO-214AB, SMC	K•A
EUP TPSMC38 GS	ESP	TPSMC33	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 29.736.3 \text{ B}; V_{WM} = 26.8 \text{ B}; I_{pp} = 31.4 \text{ A}$	DO-214AB, SMC	K•A
EVP TPSMC36A GS vs V _{BB} (t)=1.0 tak)=34.2.37 8B, V _{BB} (t)=30.1A DC-214AB, SMC k ► A EVP TPSMC39A GS vs V _{BB} (t)=1.0 tak)=35.142 8B, V _{BB} (t)=26.6A DC-214AB, SMC k ► A EVP TPSMC39A GS vs V _{BB} (t)=1.0 tak)=37.141 BN, V _{BB} (t)=25.6A DC-214AB, SMC k ► A EVP TPSMC43 GS vs V _{BB} (t)=1.0 tak)=37.141 BN, V _{BB} (t)=33.6B, t,p=28.6A DC-214AB, SMC k ► A EVP TPSMC43 GS vs V _{BB} (t)=1.0 tak)=37.141 BN, V _{BB} (t)=38.8B, t,p=28.3A DC-214AB, SMC k ► A EVP TPSMC43 GS vs V _{BB} (t)=1.0 tak)=37.141 BN, V _{BB} (t)=38.8B, t,p=28.3A DC-214AB, SMC k ► A EVP TPSMC43 GS vs V _{BB} (t)=1.0 tak)=38.747 3B, V _{BB} (t)=38.8B, t,p=28.3A DC-214AB, SMC k ► A EVP TPSMC43 GS vs V _{BB} (t)=1.0 tak)=38.747 3B, V _{BB} (t)=38.8B, t,p=28.3A DC-214AB, SMC k ► A EVP TPSMC43 GS vs V _{BB} (t)=1.0 tak)=38.747 3B, V _{BB} (t)=38.8B, t,p=28.3A DC-214AB, SMC vs vs V _{BB} (t)=10.0 tak)=64.07 28B, V _{BB} (t)=16.8B, tp=183.9A DC-214AB, SMC vs vs V _{BB} (t)=10.0 tak)=64.07 28B, V _{BB} (t)=50, t,p=183.9A DC-214AB, SMC vs vs V _{BB} (t)=10.0 tak)=64.07 28B, V _{BB} (t)=50, t,p=183.9A DC-214AB, SMC vs vs V _{BB} (t)=10.0 tak)=131.0.1.1.1.0 tak, V _{BB} (t)=10.0 tak, t=30.0 tak,	ETP	TPSMC33A	GS	VS	V _{BR} (I _T = 1.0 mA) = 31.434.7B; V _{WM} = 28.2B; I _{PP} = 32.8A	DO-214AB, SMC	K•A
EVIP TPSMC39 GS vs V _{gg,(t)} = 1.0 uA) = 35.142 9B, V _{gg,(t)} = 1.0 t _{gg,(t)} = 1.0 uA) = 37.141 0B, V _{gg,(t)} = 1.0 t _{gg,(t)} = 1.0 uA) = 37.141 0B, V _{gg,(t)} = 1.0 uA) = 38.2.142 8B, V _{gg,(t)} = 1.0 uA) = 38.747 3B, V _{gg,(t)} = 27.8.A DC-2144B, SMC (x ► A EVP TPSMC43A GS vs V _{gg,(t)} = 1.0 uA) = 38.747 3B, V _{gg,(t)} = 2.2 2.4.A DC-2144B, SMC (x ► A EVP TPSMC43A GS vs V _{gg,(t)} = 1.0 uA) = 38.747 3B, V _{gg,(t)} = 38.8 l, l _{ty} = 26.3.A DC-2144B, SMC (x ► A SMCJB GCA STM vs V _{gg,(t)} = 10.0 uA) = 68.77 3F, V _{gg,(t)} = 30.0 l, l _{ty} = 16.5 hA DC-2144B, SMC x × X V _{gg,(t)} = 10.0 uA) = 68.77 3F, V _{gg,(t)} = 10.0 l, l _{ty} = 16.9 l, l _{ty} = 13.3 9.A DC-2144B, SMC x × X V _{gg,(t)} = 10.0 uA) = 24.77 2E, V _{gg,(t)} = 10.0 l, l _{ty} = 16.9 l, l _{ty} = 16.9 l, l _{ty} = 16.9 l, l _{ty} = 14.2 A DC-2144B, SMC x × X V _{gg,(t)} = 10.0 uA) = 34.1.10.1.10.1.10.10.10.10.10.10.10.10.10.	EUP	TPSMC36	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 32.439.6B; V_{WM} = 29.1 \text{ B}; I_{pp} = 28.8 \text{ A}$	DO-214AB, SMC	K•A
EXP	EVP	TPSMC36A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 34.237.8 \text{ B}; V_{WM} = 30.8 \text{ B}; I_{pp} = 30.1 \text{ A}$	DO-214AB, SMC	K•A
EYP TPSMC433 GS vs V _{BR} (l ₁ =1.0 mA)=38.747.3B, V _{BM} =34.8B, l _{bp} =24.2A DO-214AB, SMC K=A EZP TPSMC43A GS vs V _{BR} (l ₁ =1.0 mA)=40.945.2B, V _{BM} =38.8B, l _{bp} =26.3A DO-214AB, SMC K=A FBE SMCJ8.0CA STM vs V _{BR} (l ₁ =1.0 mA)=6.67767B, V _{BM} =6.0B, l _{bp} =16.5B, A FBC SMCJ8.0CA STM vs V _{BR} (l ₁ =1.0 mA)=6.67767B, V _{BM} =6.0B, l _{bp} =16.30.A DO-214AB, SMC x=x FBC SMCJ8.0CA STM vs V _{BR} (l ₁ =1.0 mA)=6.40726B, V _{BM} =6.5B, l _{bp} =163.0A DO-214AB, SMC x=x FBC SMCJ8.0CA STM vs V _{BR} (l ₁ =1.0 mA)=6.40726B, V _{BM} =6.5B, l _{bp} =163.0A DO-214AB, SMC x=x FBF SMCJ10CA STM vs V _{BR} (l ₁ =1.0 mA)=13.3016.90B, V _{BM} =10.0B, l _{bp} =68.2A DO-214AB, SMC x=x FBF SMCJ13CA STM vs V _{BR} (l ₁ =1.0 mA)=13.3016.90B, V _{BM} =10.0B, l _{bp} =68.2A DO-214AB, SMC x=x FBL SMCJ13CA STM vs V _{BR} (l ₁ =1.0 mA)=13.3016.90B, V _{BM} =13.0B, l _{bp} =68.0A DO-214AB, SMC x=x FBL SMCJ13CA STM vs V _{BR} (l ₁ =1.0 mA)=13.3016.90B, V _{BM} =13.0B, l _{bp} =68.0A DO-214AB, SMC x=x FBL SMCJ13CA STM vs V _{BR} (l ₁ =1.0 mA)=12.3016.90B, V _{BM} =15.0B, l _{bp} =68.0A DO-214AB, SMC x=x FBL SMCJ13CA STM vs V _{BR} (l ₁ =1.0 mA)=22.0025.30B, V _{BM} =18.0B, l _{bp} =64.6A DO-214AB, SMC x=x FBL SMCJ2CA STM vs V _{BR} (l ₁ =1.0 mA)=22.2025.50B, V _{BM} =18.0B, l _{bp} =64.6A DO-214AB, SMC x=x FBD SMCJ2CA STM vs V _{BR} (l ₁ =1.0 mA)=22.2025.50B, V _{BM} =20.0B, l _{bp} =46.6A DO-214AB, SMC x=x FBD SMCJ2CA STM vs V _{BR} (l ₁ =1.0 mA)=28.9033.20B, V _{BM} =20.0B, l _{bp} =33.0A DO-214AB, SMC x=x FBD SMCJ2CA STM vs V _{BR} (l ₁ =1.0 mA)=36.7021.10B, V _{BM} =20.0B, l _{bp} =33.0A DO-214AB, SMC x=x FBD SMCJ2CA STM vs V _{BR} (l ₁ =1.0 mA)=36.7021.10B, V _{BM} =20.0B, l _{bp} =33.0A DO-214AB, SMC x=x FBD SMCJ2CA STM vs V _{BR} (l ₁ =1.0 mA)=36.7037.70B, V _{BM} =20.0B, l _{bp} =33.0A DO-214AB, SMC x=x FBD SMCJ2CA STM vs V _{BR} (l ₁ =1.0 mA)=36.7037.70B, V _{BM} =20.0B, l _{bp} =33.0A DO-214AB, SMC x=x FBD SMCJ2CA STM vs V _{BR} (l ₁ =1.0 mA)=36.7021.0B, V _{BM} =20.0B, l _{bp} =33.0A DO-214AB, SMC x=x FBD SMCJ2CA STM vs V _{BR} (l ₁ =1.0 mA)=36.7037.70B, V _{BM} =20.0B, l _{bp} =33.0A DO-214AB, SMC x=x FBD SMCJ2CA STM vs V _{BR} (l	EWP	TPSMC39	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 35.142.9 \text{B; } V_{WM} = 31.6 \text{B; } I_{pp} = 26.6 \text{A}$	DO-214AB, SMC	K•A
EZP	EXP	TPMSC39A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 37.141.0 \text{ B; } V_{WM} = 33.3 \text{ B; } I_{pp} = 27.8 \text{ A}$	DO-214AB, SMC	K•A
FBB SMCJB CCA STM vs VBs(H; = 10.0 MA) = 6.677.67B, VBs, W= 5.0 B, Ipp = 145.6A DO-214AB, SMC x × x	EYP	TPSMC43	GS	VS	V _{BR} (I _T = 1.0 mA) = 38.747.3B; V _{MM} = 34.8B; I _{PP} = 24.2A	DO-214AB, SMC	K•A
## FBC	EZP	TPSMC43A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 40.945.2B; V_{WM} = 36.8 \text{ B}; I_{pp} = 25.3 \text{ A}$	DO-214AB, SMC	K•A
## FBC	FBB	SMCJ6.0CA	STM	VS	V _{BR} (I _T = 10.0 mA) = 6.677.67B; V _{WM} = 6.0B; I _{PP} = 145.6A	DO-214AB, SMC	χ●χ
### FBD	FBC	SMCJ6.5CA	STM	VS	$V_{BR}(I_T = 10.0 \text{ mA}) = 7.228.30 \text{ B}; V_{WM} = 6.5 \text{ B}; I_{pp} = 133.9 \text{ A}$	DO-214AB, SMC	χ●χ
FBF SMC_1/10CA STM VS V _{BR} (I ₁ = 1 0.mA) = 11.1014.10 B, V _{WW} = 10.0 B, I _{bp} = 79.8 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 13.3016.90 B, V _{WW} = 12.0 B, I _{bp} = 68.2 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 14.0 M, V _{WW} = 13.0 B, I _{bp} = 68.2 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 14.0 M, V _{WW} = 13.0 B, I _{bp} = 68.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 14.0 M, V _{WW} = 13.0 B, I _{bp} = 16.0 B, I _{bp} = 68.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 12.0 D, V _{WW} = 13.0 B, I _{bp} = 68.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 20.0025.30 B, V _{WW} = 10.0 B, I _{bp} = 46.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 20.0025.30 B, V _{WW} = 20.0 B, I _{bp} = 46.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 26.7030.70 B, V _{WW} = 20.0 B, I _{bp} = 46.3 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 26.7030.70 B, V _{WW} = 20.0 B, I _{bp} = 38.6 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 26.7030.70 B, V _{WW} = 20.0 B, I _{bp} = 38.6 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 26.7030.70 B, V _{WW} = 20.0 B, I _{bp} = 33.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 26.7030.70 B, V _{WW} = 20.0 B, I _{bp} = 33.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 26.7030.70 B, V _{WW} = 20.0 B, I _{bp} = 23.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 30.0.4.20 B, V _{WW} = 20.0 B, I _{bp} = 23.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 30.0.4.20 B, V _{WW} = 30.0 B, I _{bp} = 20.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 30.0.4.20 B, V _{WW} = 30.0 B, I _{bp} = 20.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 30.0.4.20 B, V _{WW} = 30.0 B, I _{bp} = 20.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 30.0.4.20 B, V _{WW} = 30.0 B, I _{bp} = 16.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 30.0.4.20 B, V _{WW} = 30.0 B, I _{bp} = 16.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 30.0.4.20 B, V _{WW} = 30.0 B, I _{bp} = 16.0 A DO-2 14AB, SMC ×× V _{BR} (I ₁ = 1 0.mA) = 30.0.4.20 B, V _{WW} = 30.0 B, I _{bp} = 16.0 A	FBCA	SMCJ5.0CA	STM	VS	V _{BR} (I _T = 10.0 mA) = 6.407.25B; V _{WM} = 5.0B; I _{PP} = 163.0A	DO-214AB, SMC	х∙х
## PBH	FBD	SMCJ8.5CA	STM	VS	V _{BR} (I _T = 1.0 mA) = 9.4410.82B; V _{WM} = 8.5B; I _{PP} = 104.2A	DO-214AB, SMC	х∙х
FBI SMCJ13CA STM vs V _{BR} (I ₁ = 1.0 mA) = 14.4018.20 B, V _{WM} = 13.0 B, I _{PP} = 63.0 A DO-214AB, SMC x × x	FBF	SMCJ10CA	STM	VS	V _{BR} (I _T = 1.0 mA) = 11.1014.10 B; V _{WM} = 10.0 B; I _{pp} = 79.8 A	DO-214AB, SMC	х∙х
FBL SMCJ16CA STM vs V _{BR} (I ₁ = 1.0 mA) = 16.7021.10 B, V _{WM} = 15.0 B, I _{PP} = 56.8 A DO-214AB, SMC x × x × x × x × x × x × x × x × x × x	FBH	SMCJ12CA	STM	VS	V _{BB} (I _T = 1.0 mA) = 13.3016.90 B; V _{WM} = 12.0B; I _{PP} = 68.2A	DO-214AB, SMC	х∙х
## FBL SMCJ18CA STM vs V _{BR} (l ₁ =1 0.mA)=20.0025.30 B, V _{WM} = 18.0 B, l ₉₅ =46.6 A DC-214AB, SMC x x x FBM SMCJ2CCA STM vs V _{BR} (l ₁ =1 0.mA)=22.2025.50 B, V _{WM} = 20.0 B, l ₉₅ =46.3 A DC-214AB, SMC x x x FBD SMCJ2CCA STM vs V _{BR} (l ₁ =1 0.mA)=22.2025.50 B, V _{WM} = 20.0 B, l ₉₅ =46.3 A DC-214AB, SMC x x x FBD SMCJ2CCA STM vs V _{BR} (l ₁ =1 0.mA)=24.4028.00 B, V _{WM} = 20.0 B, l ₉₅ =36.6 A DC-214AB, SMC x x x FBD SMCJ2CCA STM vs V _{BR} (l ₁ =1 0.mA)=28.9033.0 B, V _{WM} = 20.0 B, l ₉₅ =36.6 A DC-214AB, SMC x x x x x x x y x y x y x y x y x	FBI	SMCJ13CA	STM	VS	V _{BR} (I _T = 1.0 mA) = 14.4018.20 B; V _{WM} = 13.0 B; I _{PP} = 63.0 A	DO-214AB, SMC	х∙х
FBM SMCJ20CA STM vs V _{BR} (I _I = 1 0 mA) = 22 2025.50 B, V _{WM} = 20 0 B, I _D = 46.3 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 22 4025.00 B, V _{WM} = 20 0 B, I _D = 46.3 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 24.4028.00 B, V _{WM} = 24.00 B, I _D = 36.6 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 24.0028.00 B, V _{WM} = 24.00 B, I _D = 36.6 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 28.9032.00 B, V _{WM} = 24.00 B, I _D = 36.6 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 33.0042.00 B, V _{WM} = 24.00 B, I _D = 33.0 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 33.0042.00 B, V _{WM} = 24.00 B, I _D = 33.0 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 33.0042.00 B, V _{WM} = 20.00 B, I _D = 28.0 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 33.0042.00 B, V _{WM} = 30.00 B, I _D = 28.0 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 33.0042.00 B, V _{WM} = 30.00 B, I _D = 28.0 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 33.0042.40 B, V _{WM} = 30.00 B, I _D = 28.0 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 33.0042.40 B, V _{WM} = 40.00 B, I _D = 19.4 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 44.4051.10 B, V _{WM} = 40.00 B, I _D = 19.4 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 40.00.42.44.00 B, I _D = 50.00 B, I _D = 163.0 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 64.007.26.0 B, V _{WM} = 50.00 B, I _D = 165.0 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 64.007.26.0 B, V _{WM} = 50.0 B, I _D = 165.0 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 64.007.26.0 B, V _{WM} = 50.0 B, I _D = 165.0 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 64.007.26.0 B, V _{WM} = 50.0 B, I _D = 165.0 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 64.007.26.0 B, V _{WM} = 50.0 B, I _D = 165.0 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 64.007.26.0 B, V _{WM} = 50.0 B, I _D = 165.0 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 10.0 A 10.0 A 10.0 B, V _{WM} = 10.0 B, I _D = 165.0 A DO-214AB, SMC ×× V _{BR} (I _I = 1 0 mA) = 10.0 A 10.0 A 10.0	FBJ	SMCJ15CA	STM	VS		DO-214AB, SMC	х∙х
FBN SMC,122CA STM vs V _{BR} (I ₁ = 1 0 mA) = 24.4028.00 B, V _{MM} = 22.0 B, I _{DP} = 38.6 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 26.7030.70 B, V _{MM} = 24.00 B, I _{DP} = 38.6 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 26.7030.70 B, V _{MM} = 24.00 B, I _{DP} = 38.6 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 28.9033.20 B, V _{MM} = 26.0 B, I _{DP} = 38.6 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 33.3042.40 B, V _{MM} = 26.0 B, I _{DP} = 28.0 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 33.3042.40 B, V _{MM} = 26.0 B, I _{DP} = 28.0 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 36.7042.20 B, V _{MM} = 30.0 B, I _{DP} = 28.1 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 36.7042.20 B, V _{MM} = 30.0 B, I _{DP} = 28.1 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 36.7042.20 B, V _{MM} = 40.0 B, I _{DP} = 28.1 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 64.0074.60 B, V _{MM} = 40.0 B, I _{DP} = 19.4 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 64.0074.60 B, V _{MM} = 40.0 B, I _{DP} = 16.0 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 64.0074.60 B, V _{MM} = 50.0 B, I _{DP} = 16.0 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 64.0074.60 B, V _{MM} = 50.0 B, I _{DP} = 16.3 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 64.0074.60 B, V _{MM} = 50.0 B, I _{DP} = 16.3 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 64.0074.60 B, V _{MM} = 50.0 B, I _{DP} = 16.3 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 64.0076.0 B, V _{MM} = 50.0 B, I _{DP} = 16.3 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 64.0076.0 B, V _{MM} = 50.0 B, I _{DP} = 16.3 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 64.0076.0 B, V _{MM} = 50.0 B, I _{DP} = 16.3 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 10.0 Ma) = 64.0076.0 B, V _{MM} = 65.0 B, I _{DP} = 16.0 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 10.0 Ma) = 64.0076.0 B, V _{MM} = 10.0 B, I _{DP} = 10.0 A DO-214AB, SMC x × X P _{BR} (I _P = 1 0 mA) = 10.0 A, I _{DR} = 10.0 B, I _{DP} = 10.0 A DO-214AB, SMC x × X P _{BR} (I _P	FBL	SMCJ18CA	STM	vs	V _{BB} (I _T = 1.0 mA) = 20.0025.30 B; V _{MM} = 18.0B; I _{PP} = 46.6 A	DO-214AB, SMC	х∙х
FEN SMCJ2CA STM VS V _{BR} (I ₁ =1 0 mA) = 24.4028.00 B, V _{WW} = 22.0 B, I _{DP} = 42.2 A DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 26.7030.70 B, V _{WW} = 24.0 B, I _{DP} = 38.6 A DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 33.03 a DB, V _{WW} = 24.0 B, I _{DP} = 38.6 A DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 33.03 a DB, V _{WW} = 26.0 B, I _{DP} = 33.0 A DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 33.01 a DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 33.01 a DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 33.01 a DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 33.01 a DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 33.01 a DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 33.01 a DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 33.01 a DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 44.05.51 a D, V _{WW} = 30.08 I _{DP} = 26.1 A DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 44.05.51 a D, V _{WW} = 40.08 I _{DP} = 19.4 A DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 53.05 a D, V _{WW} = 40.08 I _{DP} = 16.0 A DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 53.05 a DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 64.07. 756 b V _{WW} = 50.08 I _{DP} = 16.0 A DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 64.07. 756 b V _{WW} = 50.08 I _{DP} = 16.0 A DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 64.07. 756 b V _{WW} = 50.08 I _{DP} = 16.0 A DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 64.07. 756 b V _{WW} = 50.08 I _{DP} = 145.8 A DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 67.07. 756 b V _{WW} = 50.08 I _{DP} = 145.8 A DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 67.07. 756 b V _{WW} = 50.08 I _{DP} = 145.8 A DC-214AB, SMC × × V _{BR} (I ₁ =1 0 mA) = 10.07.	FBM	SMCJ20CA	STM	vs	V _{BB} (I _T = 1.0 mA) = 22.2025.50 B; V _{MM} = 20.0 B; I _{DD} = 46.3 A	DO-214AB, SMC	х∙х
FBO SMCJ24CA STM VS V _{BR} (I _T = 1.0 mA) = 26.7030.70 B, V _{BW} = 24.0 B, I _{DP} = 38.6 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 28.9032.0 B, V _{BW} = 20.0 B, I _{DP} = 36.6 A DC-214AB, SMC × × × V _{BR} (I _T = 1.0 mA) = 28.9032.0 B, V _{BW} = 20.0 B, I _{DP} = 36.6 A DC-214AB, SMC × × × V _{BR} (I _T = 1.0 mA) = 33.042.40 B, V _{BW} = 20.0 B, I _{DP} = 28.0 A DC-214AB, SMC × × × V _{BR} (I _T = 1.0 mA) = 33.042.40 B, V _{BW} = 30.0 B, I _{DP} = 28.0 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 36.7042.20 B, V _{WM} = 30.0 B, I _{DP} = 28.1 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 36.7042.20 B, V _{WM} = 30.0 B, I _{DP} = 28.1 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 64.4051.10 B, V _{WM} = 40.0 B, I _{DP} = 28.2 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 64.4074.60 B, V _{WM} = 40.0 B, I _{DP} = 16.0 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 64.4074.60 B, V _{WM} = 50.0 B, I _{DP} = 16.0 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 64.4074.60 B, V _{WM} = 50.0 B, I _{DP} = 16.3 D A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 64.4074.60 B, V _{WM} = 50.0 B, I _{DP} = 16.3 D A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 64.4076.70 B, V _{WM} = 50.8 I _{DP} = 14.56 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 64.4076.70 B, V _{WM} = 50.8 I _{DP} = 14.56 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 64.4076.70 B, V _{WM} = 50.8 I _{DP} = 14.56 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 64.4076.70 B, V _{WM} = 50.8 I _{DP} = 14.2 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 64.4076.70 B, V _{WM} = 50.8 I _{DP} = 104.2 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 94.4.10 8.2 B, V _{WM} = 10.0 B, I _{DP} = 88.2 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 94.4.10 8.2 B, V _{WM} = 10.0 B, I _{DP} = 88.2 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 14.4016.50 B, V _{WM} = 10.0 B, I _{DP} = 69.7 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 14.4016.50 B, V _{WM} = 10.0 B, I _{DP} = 69.7 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 16.7019.2 B, V _{WM} = 10.0 B, I _{DP} = 69.7 A DC-214AB, SMC × × V _{BR} (I _T = 1.0 mA) = 16.7019.2 B, V _{WM} = 10.0 B, I _{DP} = 69.7 A DC-214AB,	FBN	SMCJ22CA	STM	VS	V _{BB} (I _T = 1.0 mA) = 24.4028.00 B; V _{MM} = 22.0B; I _{PP} = 42.2 A	DO-214AB, SMC	х∙х
FBQ SMCJ38CA STM vs V _{gB} (l ₁ =1 0 mA)=31.1035.80 B, V _{gw} =28.0 B, l _{pp} =33.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=33.0 .42.40 B, V _{gw} =30.0 B, l _{pp} =28.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=33.0 .42.40 B, V _{gw} =30.0 B, l _{pp} =28.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=43.0 C, 42.0 B, V _{gw} =30.0 B, l _{pp} =28.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=53.0 C, 61.30 B, V _{gw} =40.0 B, l _{pp} =19.4 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=53.0 C, 61.30 B, V _{gw} =40.0 B, l _{pp} =19.4 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=63.0 C, 61.30 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=64.4 C, 74.60 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=64.7 C, 76.0 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=64.7 C, 76.0 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=64.7 C, 76.0 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=64.7 C, 76.0 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=64.7 C, 76.0 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.7 C, 76.0 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, 76.0 B, V _{gw} =65.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, 76.0 B, V _{gw} =65.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, 76.0 B, V _{gw} =65.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, V _{gw} =10.0 B, l _{pp} =65.1 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, V _{gw} =10.0 B, l _{pp} =65.1 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, V _{gw} =10.0 B, l _{pp} =61.5 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, V _{gw} =10.0 B, l _{pp} =61.5 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, V _{gw} =10.0 B, l _{pp} =61.5 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, V _{gw} =10.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=20.0 C, 23.0 B, V _{gw} =20.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=20.0 C, 23.0 B, V _{gw} =20.0 B, l _{pp} =20.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=20.0 C, 23.0 B, V _{gw} =20.0 B, l _{pp} =20.0 A DC-214AB,	FB0	SMCJ24CA	STM	VS		DO-214AB, SMC	х∙х
FBQ SMCJ38CA STM vs V _{gB} (l ₁ =1 0 mA)=31.1035.80 B, V _{gw} =28.0 B, l _{pp} =33.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=33.0 .42.40 B, V _{gw} =30.0 B, l _{pp} =28.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=33.0 .42.40 B, V _{gw} =30.0 B, l _{pp} =28.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=43.0 C, 42.0 B, V _{gw} =30.0 B, l _{pp} =28.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=53.0 C, 61.30 B, V _{gw} =40.0 B, l _{pp} =19.4 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=53.0 C, 61.30 B, V _{gw} =40.0 B, l _{pp} =19.4 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=63.0 C, 61.30 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=64.4 C, 74.60 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=64.7 C, 76.0 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=64.7 C, 76.0 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=64.7 C, 76.0 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=64.7 C, 76.0 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=64.7 C, 76.0 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.7 C, 76.0 B, V _{gw} =50.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, 76.0 B, V _{gw} =65.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, 76.0 B, V _{gw} =65.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, 76.0 B, V _{gw} =65.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, V _{gw} =10.0 B, l _{pp} =65.1 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, V _{gw} =10.0 B, l _{pp} =65.1 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, V _{gw} =10.0 B, l _{pp} =61.5 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, V _{gw} =10.0 B, l _{pp} =61.5 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, V _{gw} =10.0 B, l _{pp} =61.5 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=16.0 C, V _{gw} =10.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=20.0 C, 23.0 B, V _{gw} =20.0 B, l _{pp} =16.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=20.0 C, 23.0 B, V _{gw} =20.0 B, l _{pp} =20.0 A DC-214AB, SMC × × V _{gB} (l ₁ =1 0 mA)=20.0 C, 23.0 B, V _{gw} =20.0 B, l _{pp} =20.0 A DC-214AB,	FBP	SMCJ26CA	STM	VS	V _{BB} (I _T = 1.0 mA) = 28.9033.20 B; V _{MM} = 26.0 B; I _{PP} = 35.6 A	DO-214AB, SMC	х∙х
FBS SMCJ33CA STM vs V _{BR} (I _T = 1 0 mA) = 36.7042.20 B, V _{MM} = 33.0 B, I _{MP} = 28.1 A DC-214AB, SMC ×× FBU SMCJ48CA STM vs V _{BR} (I _T = 1 0 mA) = 44.4061.10 B, V _{MM} = 40.0 B, I _{MP} = 29.2 A DC-214AB, SMC ×× FBU SMCJ48CA STM vs V _{BR} (I _T = 1 0 mA) = 64.074.60 B, V _{MM} = 48.0 B, I _{MP} = 19.4 A DC-214AB, SMC ×× FBU SMCJ58CA STM vs V _{BR} (I _T = 10 0 mA) = 64.074.60 B, V _{MM} = 48.0 B, I _{MP} = 19.4 A DC-214AB, SMC ×× FBU SMCJ58CA STM vs V _{BR} (I _T = 10.0 mA) = 64.074.60 B, V _{MM} = 50.0 B, I _{MP} = 163.0 A DC-214AB, SMC ×× FBU SMCJ56A STM vs V _{BR} (I _T = 10.0 mA) = 64.074.60 B, V _{MM} = 50.B, I _{MP} = 163.0 A DC-214AB, SMC ×× FBU SMCJ56A STM vs V _{BR} (I _T = 10.0 mA) = 64.074.60 B, V _{MM} = 50.B, I _{MP} = 163.0 A DC-214AB, SMC ×× FBU SMCJ56A STM vs V _{BR} (I _T = 10.0 mA) = 72.2 B, 30B, V _{MM} = 5.8 B, I _{MP} = 104.2 A DC-214AB, SMC ×× FBU SMCJ10A STM vs V _{BR} (I _T = 1 0 mA) = 9.4410.82 B, V _{MM} = 8.5 B, I _{MP} = 104.2 A DC-214AB, SMC ×× FBU SMCJ10A STM vs V _{BR} (I _T = 1 0 mA) = 11.1012.80 B, V _{MM} = 10.0 B, I _{MP} = 58.8 A DC-214AB, SMC ×× FBU SMCJ10A STM vs V _{BR} (I _T = 1 0 mA) = 11.0.0 A D, I _{MM} = 10.80 B, I _{MM} = 13.00 B, I _{MM} = 13.0	FBQ	SMCJ28CA	STM	VS	V _{BB} (I _T = 1.0 mA) = 31.1035.80 B; V _{MM} = 28.0 B; I _{PP} = 33.0 A	DO-214AB SMC	х∙х
FBU SMCJ40CA STM vs V _{BR} (I ₁ = 1.0 mA) = 44.4051.10 B, V _{MM} = 40.0 B, I _{PP} = 32.2 A DO-214AB, SMC x × x × x SMCJ40CA STM vs V _{BR} (I ₁ = 1.0 mA) = 53.0061.30 B, V _{MM} = 40.0 B, I _{PP} = 19.4 A DO-214AB, SMC x × x × x SMCJ50CA STM vs V _{BR} (I ₁ = 1.0 mA) = 64.407.6 B, I _{VMM} = 50.0 B, I _{PP} = 16.0 A DO-214AB, SMC x × x × x SMCJ50CA STM vs V _{BR} (I ₁ = 1.0 mA) = 64.07.6 B, I _{VMM} = 50.0 B, I _{PP} = 16.0 A DO-214AB, SMC x × x × x SMCJ50CA STM vs V _{BR} (I ₁ = 10.0 mA) = 64.07.6 B, I _{VMM} = 6.0 B, I _{PP} = 133.9 A DO-214AB, SMC x × x × x SMCJ50CA STM vs V _{BR} (I ₁ = 10.0 mA) = 72.28 DB, I _{VMM} = 6.0 B, I _{PP} = 16.5 B DO-214CAB, SMC x × x × x SMCJ50CA STM vs V _{BR} (I ₁ = 10.0 mA) = 10.2 B, I _{VMM} = 6.0 B, I _{PP} = 10.0 B, I _P	FBR	SMCJ30CA	STM	VS	V _{BR} (I _T = 1.0 MA) = 33.3042.40 B; V _{WM} = 30.0 B; I _{PP} = 28.0 A	DO-214AB, SMC	х∙х
FBIW SMCJ48CA STM vs V _{BR} (I ₁ =1.0 mA)=63.3061.30 B, V _{WM} =48.0 B, I _{DP} =19.4 A DC-214AB, SMC x x x N V _{BR} (I ₁ =1.0 mA)=64.4074.60 B, V _{WM} =50.8 I _{DP} =16.0 A DC-214AB, SMC x x x N V _{BR} (I ₁ =1.0 mA)=64.074.60 B, V _{WM} =50.8 I _{DP} =163.0 A DC-214AB, SMC x x x N V _{BR} (I ₁ =1.0 mA)=64.074.60 B, V _{WM} =50.8 I _{DP} =148.0 A DC-214AB, SMC x x x N V _{BR} (I ₁ =1.0 mA)=64.074.8 B, V _{WM} =50.8 I _{DP} =148.0 A DC-214AB, SMC x x x N V _{BR} (I ₁ =1.0 mA)=94.0 A, 10.8 2 B, V _{WM} =50.8 I _{DP} =145.0 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=94.0 A, 10.8 2 B, V _{WM} =50.8 I _{DP} =143.9 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=94.0 A, 10.8 2 B, V _{WM} =50.8 I _{DP} =104.2 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=94.0 A, 10.8 2 B, V _{WM} =50.8 I _{DP} =104.2 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=11.0 A, 12.8 B, V _{WM} =10.0 B, I _{DP} =58.2 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=11.0 A, 12.8 B, V _{WM} =10.0 B, I _{DP} =58.2 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=11.0 A, 12.8 B, V _{WM} =10.0 B, I _{DP} =69.7 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=11.0 A, 12.3 B, V _{WM} =10.0 B, I _{DP} =69.7 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=10.0 A, 10.3 B, V _{WM} =10.0 B, I _{DP} =69.7 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=10.0 A, 10.3 B, V _{WM} =10.0 B, I _{DP} =69.7 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=10.0 A, 10.0 A, 10.0 B, I _{DP} =69.7 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=10.0 A, 10.0 A, 10.0 B, I _{DP} =61.5 B, I _{DP} =61.5 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=20.0 B, I _{DM} =10.0 B, I _{DP} =61.5 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=20.0 B, I _{DM} =10.0 B, I _{DP} =61.5 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=20.0 A, 10.0 B, I _{DM} =10.0 B, I _{DP} =61.5 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=20.0 B, I _{DM} =10.0 B, I _{DP} =61.5 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=20.0 B, I _{DM} =20.0 B, I _{DP} =20.0 B, I _{DP} =20.0 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=20.0 B, I _{DM} =20.0 B, I _{DP} =20.0 B, I _{DP} =20.0 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=30.0 A, 20.0 B, I _{DM} =20.0 B, I _{DP} =20.0 A DC-214AB, SMC x x X V _{BR} (I ₁ =1.0 mA)=30.0 A, 20.0 B, I _{DM} =20.0 B, I _{DP} =20.0 A DC	FBS	SMCJ33CA	STM	VS	V _{BR} (I _T = 1.0 mA) = 36.7042.20 B; V _{WM} = 33.0 B; I _{PP} = 28.1 A	DO-214AB, SMC	х∙х
FBZ SMCJ58CA STM vs V _{BR} (I ₁ = 1.0 мA) = 64.4074.60 B, V _{MM} = 58.0 B, I ₉₅ = 16.0 A DC-214AB, SMC K = A FUB SMCJ50A STM vs V _{BR} (I ₁ = 10.0 MA) = 64.074.60 B, V _{MM} = 5.0 B, I ₉₅ = 16.3 DA DC-214AB, SMC K = A FUB SMCJ60A STM vs V _{BR} (I ₁ = 10.0 MA) = 6.6 C 7.72 B, V _{MM} = 6.0 B, I ₉₅ = 16.3 DA DC-214AB, SMC K = A FUD SMCJ65A STM vs V _{BR} (I ₁ = 10.0 MA) = 6.6 C 7.72 B, V _{MM} = 6.0 B, I ₉₅ = 145.6 A DC-214AB, SMC K = A FUD SMCJ65A STM vs V _{BR} (I ₁ = 10.0 MA) = 9.4410.82 B, V _{MM} = 8.0 B, I ₉₅ = 104.2 A DC-214AB, SMC K = A FUB SMCJ10A STM vs V _{BR} (I ₁ = 1.0 MA) = 9.4410.82 B, V _{MM} = 10.0 B, I ₉₅ = 88.2 A DC-214AB, SMC K = A FUB SMCJ13A STM vs V _{BR} (I ₁ = 1.0 MA) = 11.0 DA, 11.3 DB, V _{MM} = 12.0 B, I ₉₅ = 75.3 A DC-214AB, SMC K = A FUB SMCJ13A STM vs V _{BR} (I ₁ = 1.0 MA) = 14.4016.50 B, V _{MM} = 12.0 B, I ₉₅ = 69.7 A DC-214AB, SMC K = A FUB SMCJ13A STM vs V _{BR} (I ₁ = 1.0 MA) = 16.7019.2 DB, V _{MM} = 10.0 B, I ₉₅ = 69.7 A DC-214AB, SMC K = A FUB SMCJ13A STM vs V _{BR} (I ₁ = 1.0 MA) = 16.7019.2 DB, V _{MM} = 10.0 B, I ₉₅ = 69.7 A DC-214AB, SMC K = A FUB SMCJ10A STM vs V _{BR} (I ₁ = 1.0 MA) = 20.0023.3 DB, V _{MM} = 10.0 B, I ₉₅ = 69.7 A DC-214AB, SMC K = A FUB SMCJ20A STM vs V _{BR} (I ₁ = 1.0 MA) = 20.0023.3 DB, V _{MM} = 10.0 B, I ₉₅ = 69.7 A DC-214AB, SMC K = A FUB SMCJ20A STM vs V _{BR} (I ₁ = 1.0 MA) = 22.0.22 DB, V _{MM} = 10.0 B, I ₉₅ = 69.7 A DC-214AB, SMC K = A FUB SMCJ20A STM vs V _{BR} (I ₁ = 1.0 MA) = 22.0.22 DB, V _{MM} = 10.0 B, I ₉₅ = 69.7 A DC-214AB, SMC K = A FUB SMCJ20A STM vs V _{BR} (I ₁ = 1.0 MA) = 22.0.22 DB, V _{MM} = 10.0 B, I ₉₅ = 69.7 A DC-214AB, SMC K = A FUB SMCJ20A STM vs V _{BR} (I ₁ = 1.0 MA) = 28.00.0 B, V _{MM} = 10.0 B, I ₉₅ = 69.7 A DC-214AB, SMC K = A FUB SMCJ20A STM vs V _{BR} (I ₁ = 1.0 MA) = 28.00.0 B, V _{MM} = 20.0 B, I ₉₅ = 23.6 A DC-214AB, SMC K = A FUB SMCJ20A STM vs V _{BR} (I ₁ = 1.0 MA) = 28.00.0 B, V _{MM} = 20.0 B, I ₉₅ = 33.6 A DC-214AB, SMC K = A FUB SMCJ20A STM vs V _{BR} (I ₁ = 1.0 MA) = 28.00.0 B, V _{MM} = 20.0 B, I ₉₅ = 23.0 A D	FBU	SMCJ40CA	STM	VS	V _{BR} (I _T = 1.0 mA) = 44.4051.10 B; V _{MM} = 40.0 B; I _{PP} = 23.2 A	DO-214AB, SMC	х∙х
FUL SMCJB0A STM VS VB(H;=10.0 MA)=6.407.25B, V _{MM} =5.0B, I _{pp} =163.0A DC-214AB, SMC K=A FUB SMCJB0A STM VS VB(H;=10.0 MA)=6.677.67B, V _{Mm} =6.0B, I _{pp} =165.0A DC-214AB, SMC K=A FUL SMCJB5A STM VS V _B (H;=10.0 MA)=7.228.30B, V _{Mm} =6.5B, I _{pp} =13.9A DC-214AB, SMC K=A FUL SMCJBA STM VS V _B (H;=10.0 MA)=7.228.30B, V _{Mm} =6.5B, I _{pp} =10.92A DC-214AB, SMC K=A FUH SMCJI0A STM VS V _B (H;=10.0 MA)=11.10, 12.80B, V _{Mm} =10.0B, I _{pp} =10.92A DC-214AB, SMC K=A FUH SMCJI0A STM VB V _B (H;=10.0 MA)=11.10, 12.80B, V _{Mm} =10.0B, I _{pp} =6.81.2A DC-214AB, SMC K=A FUH SMCJI0A STM VB V _B (H;=10.0 MA)=13.0015.30B, V _{Mm} =10.0B, I _{pp} =6.81.A DC-214AB, SMC K=A FUL SMCJI3A STM VB V _B (H;=10.0 MA)=16.7019.20B, V _{Mm} =10.0B, I _{pp} =61.5A DC-214AB, SMC K=A FUL SMCJI3A STM VS V _B (H;=10.0 MA)=16.7019.20B, V _{Mm} =10.0B, I _{pp} =61.5A DC-214AB, SMC K=A FUL SMCJI3A STM VS V _B (H;=10.0 MA)=20.0023.0B, V _{Mm} =10.0B, I _{pp} =61.5A DC-214AB, SMC K=A FUL SMCJI2A STM VS V _B (H;=10.0 MA)=20.0023.0B, V _{Mm} =10.0B, I _{pp} =61.5A DC-214AB, SMC K=A FUL SMCJI2A STM VS V _B (H;=10.0 MA)=20.0023.0B, V _{Mm} =10.0B, I _{pp} =61.4A DC-214AB, SMC K=A FUL SMCJI2A STM VS V _B (H;=10.0 MA)=28.7028.00B, V _{Mm} =20.0B, I _{pp} =10.84.2 A DC-214AB, SMC K=A FUL SMCJI2A STM VS V _B (H;=10.0 MA)=28.7030.70B, V _{Mm} =20.0B, I _{pp} =61.5A DC-214AB, SMC K=A FUL SMCJI2AA STM VS V _B (H;=10.0 MA)=28.7030.70B, V _{Mm} =20.0B, I _{pp} =53.6A DC-214AB, SMC K=A FUL SMCJI2AA STM VS V _B (H;=10.0 MA)=28.7030.70B, V _{Mm} =20.0B, I _{pp} =53.6A DC-214AB, SMC K=A FUL SMCJI2AA STM VS V _B (H;=10.0 MA)=33.3042.40B, V _{Mm} =20.0B, I _{pp} =62.2A DC-214AB, SMC K=A FUL SMCJI2AA STM VS V _B (H;=10.0 MA)=33.3042.40B, V _{Mm} =20.0B, I _{pp} =28.0A DC-214AB, SMC K=A FUL SMCJI2AA STM VS V _B (H;=10.0 MA)=33.0042.40B, V _{Mm} =20.0B, I _{pp} =28.0A DC-214AB, SMC K=A FUL SMCJI2AA STM VS V _B (H;=10.0 MA)=33.0042.40B, V _{Mm} =20.0B, I _{pp} =28.0A DC-214AB, SMC K=A FUL SMCJI2AA STM VS V _B (H;=10.0 MA)=33.0042.40B, V _{Mm} =28.0B, I _{pp} =28.1A DC-214AB, SMC K=A FUL SMCJI2AA STM VS V _B (H;=10.0 MA)=36.7061.0B, V _{Mm}	FBW	SMCJ48CA	STM	VS	V _{BB} (I _T = 1.0 mA) = 53.3061.30 B; V _{WM} = 48.0 B; I _{PP} = 19.4 A	DO-214AB, SMC	х∙х
FUB SMCJ86A STM vs V _{BB} (I _T = 10.0 MA) = 6.677 67B, V _{MM} = 6.0 B, I _{BP} = 145.6A DC-214AB, SMC K + A FUC SMCJ85A STM vs V _{BB} (I _T = 10.0 MA) = 7.228.20B, V _{MM} = 6.5B, I _{BP} = 143.39 A DC-214AB, SMC K + A FUB SMCJ85A STM vs V _{BB} (I _T = 10.0 MA) = 7.228.20B, V _{MM} = 6.5B, I _{BP} = 104.2A DC-214AB, SMC K + A FUB SMCJ10A STM vs V _{BB} (I _T = 10.0 MA) = 11.012.80 B, V _{MM} = 15.0B, I _{BP} = 104.2A DC-214AB, SMC K + A FUB SMCJ10A STM vs V _{BB} (I _T = 10.0 MA) = 11.012.80 B, V _{MM} = 10.0B, I _{BP} = 104.2A DC-214AB, SMC K + A FUB SMCJ10A STM vs V _{BB} (I _T = 10.0 MA) = 13.3015.30 B, V _{MM} = 10.0B, I _{BP} = 153.3A DC-214AB, SMC K + A FUB SMCJ10A STM vs V _{BB} (I _T = 10.0 MA) = 14.00.16.50 B, V _{MM} = 10.0B, I _{BP} = 66.7A DC-214AB, SMC K + A FUB SMCJ10A STM vs V _{BB} (I _T = 10.0 MA) = 16.7019.20 B, V _{MM} = 15.0B, I _{BP} = 66.15 A DC-214AB, SMC K + A FUB SMCJ10A STM vs V _{BB} (I _T = 10.0 MA) = 20.0023.30 B, V _{MM} = 15.0B, I _{BP} = 61.5A DC-214AB, SMC K + A FUB SMCJ20A STM vs V _{BB} (I _T = 10.0 MA) = 22.0028.10 B, V _{MM} = 20.0B, I _{BP} = 61.5A DC-214AB, SMC K + A FUB SMCJ20A STM vs V _{BB} (I _T = 10.0 MA) = 22.0028.10 B, V _{MM} = 20.0B, I _{BP} = 61.5A DC-214AB, SMC K + A FUB SMCJ20A STM vs V _{BB} (I _T = 10.0 MA) = 22.0028.10 B, V _{MM} = 20.0B, I _{BP} = 61.5A DC-214AB, SMC K + A FUB SMCJ20A STM vs V _{BB} (I _T = 10.0 MA) = 26.7030.70 B, V _{MM} = 20.0B, I _{BP} = 38.6 A DC-214AB, SMC K + A FUB SMCJ20A STM vs V _{BB} (I _T = 10.0 MA) = 26.7030.70 B, V _{MM} = 20.0B, I _{BP} = 33.0 A DC-214AB, SMC K + A FUB SMCJ20A STM vs V _{BB} (I _T = 10.0 MA) = 33.01.42.40 B, V _{MM} = 30.0B, I _{BP} = 28.0 A DC-214AB, SMC K + A FUB SMCJ30A STM vs V _{BB} (I _T = 10.0 MA) = 33.00.42.40 B, V _{MM} = 30.0B, I _{BP} = 28.0 A DC-214AB, SMC K + A FUB SMCJ30A STM vs V _{BB} (I _T = 10.0 MA) = 33.00.61.30 B, V _{MM} = 30.0B, I _{BP} = 28.0 A DC-214AB, SMC K + A FUB SMCJ30A STM vs V _{BB} (I _T = 10.0 MA) = 33.00.61.30 B, V _{MM} = 30.0B, I _{BP} = 28.0 A DC-214AB, SMC K + A FUB SMCJ30A STM vs V _{BB} (I _T = 10.0 MA) = 33.00.61.30 B, V _{MM} = 30.0B, I _{BP} = 28.0 A DC-	FBZ	SMCJ58CA	STM	vs	V _{BR} (I _T = 1.0 mA) = 64.4074.60 B; V _{WM} = 58.0 B; I _{pp} = 16.0 A	DO-214AB, SMC	х∙х
FUL SMCJ16A STM VS V _{BR} (I ₁ =10.0MA)=7.228.30B, V _{MM} =6.5B, I _{BP} =133.9A DC-214AB, SMC K=A FUD SMCJ16A STM VS V _{BR} (I ₁ =10.0MA)=9.4410.82B, V _{MM} =6.5B, I _{BP} =104.2A DC-214AB, SMC K=A FUH SMCJ16A STM VS V _{BR} (I ₁ =10.0MA)=11.1012.80B, V _{MM} =10.0B, I _{BP} =68.2A DC-214AB, SMC K=A FUH SMCJ16A STM VS V _{BR} (I ₁ =10.0MA)=13.0015.30B, V _{MM} =10.0B, I _{BP} =69.7A DC-214AB, SMC K=A FUI SMCJ16A STM VS V _{BR} (I ₁ =10.0MA)=13.0015.0B, V _{MM} =10.0B, I _{BP} =69.7A DC-214AB, SMC K=A FUI SMCJ16A STM VS V _{BR} (I ₁ =10.0MA)=10.7019.20B, V _{MM} =10.0B, I _{BP} =61.5A DC-214AB, SMC K=A FUI SMCJ16A STM VS V _{BR} (I ₁ =10.0MA)=20.0023.30B, V _{MM} =10.0B, I _{BP} =61.5A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁ =10.0MA)=20.0023.30B, V _{MM} =10.0B, I _{BP} =61.5A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁ =10.0MA)=20.0023.30B, V _{MM} =10.0B, I _{BP} =61.5A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁ =10.0MA)=20.0023.30B, V _{MM} =20.0B, I _{BP} =42.2A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁ =10.0MA)=20.0030.70B, V _{MM} =20.0B, I _{BP} =42.2A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁ =10.0MA)=26.7030.70B, V _{MM} =20.0B, I _{BP} =33.6A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁ =10.0MA)=30.00.28.00B, V _{MM} =20.0B, I _{BP} =30.2A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁ =10.0MA)=30.00.28.00B, V _{MM} =20.0B, I _{BP} =20.2A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁ =10.0MA)=30.00.24.20B, V _{MM} =20.0B, I _{BP} =20.0A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁ =10.0MA)=30.00.24.20B, V _{MM} =30.0B, I _{BP} =20.0A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁ =10.0MA)=30.7042.20B, V _{MM} =30.0B, I _{BP} =20.0A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁ =10.0MA)=30.7014.20B, V _{MM} =30.0B, I _{BP} =20.0A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁ =10.0MA)=30.7014.20B, V _{MM} =30.0B, I _{BP} =20.0A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁ =10.0MA)=30.0014.20B, V _{MM} =30.0B, I _{BP} =20.0A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁ =10.0MA)=30.0014.20B, V _{MM} =30.0B, I _{BP} =20.0A DC-214AB, SMC K=A FUI SMCJ20A STM VS V _{BR} (I ₁	FUA	SMCJ5.0A	STM	VS	V _{BR} (I _T =10.0 mA)=6.407.25B; V _{WM} =5.0B; I _{PP} =163.0A	DO-214AB, SMC	K∙A
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	FUB	SMCJ6.0A	STM	VS	V _{BR} (I _T = 10.0 mA) = 6.677.67B; V _{WM} = 6.0B; I _{pp} = 145.6A	DO-214AB, SMC	K∙A
FUF SMCJ10A STM vs V _{BR} (I _T = 1.0 мA) = 11.10 12.80 B, V _{BM} = 10.0 B, I _{bp} = 88.2 A DC-214AB, SMC K = A FUH SMCJ12A STM vs V _{BR} (I _T = 1.0 mA) = 13.30 15.30 B, V _{BM} = 12.0 B, I _{bp} = 75.3 A DC-214AB, SMC K = A FUL SMCJ13A STM vs V _{BR} (I _T = 1.0 mA) = 13.00 15.30 B, V _{BM} = 13.0 B, I _{bp} = 69.7 A DC-214AB, SMC K = A FUL SMCJ13A STM vs V _{BR} (I _T = 1.0 mA) = 16.70 19.20 B, I _{bm} = 16.0 B, I _{bp} = 69.7 A DC-214AB, SMC K = A FUL SMCJ13A STM vs V _{BR} (I _T = 1.0 mA) = 20.00 23.30 B, V _{BM} = 13.0 B, I _{bp} = 51.4 A DC-214AB, SMC K = A FUN SMCJ20A STM vs V _{BR} (I _T = 1.0 mA) = 22.00 23.0 B, V _{BM} = 20.0 B, I _{bp} = 51.4 A DC-214AB, SMC K = A FUN SMCJ22A STM vs V _{BR} (I _T = 1.0 mA) = 22.00 28.10 B, V _{BM} = 20.0 B, I _{bp} = 36.4 DC-214AB, SMC K = A FUD SMCJ26A STM vs V _{BR} (I _T = 1.0 mA) = 28.70 30.70 B, V _{BM} = 20.0 B, I _{bp} = 36.4 DC-214AB, SMC K = A FUD SMCJ26A STM vs V _{BR} (I _T = 1.0 mA) = 28.90 36.0 B, V _{BM} = 20.0 B, I _{bp} = 30.4 DC-214AB, SMC K = A FUR SMCJ28A STM vs V _{BR} (I _T = 1.0 mA) = 33.30 42.40 B, V _{BM} = 20.0 B, I _{bp} = 30.0 A DC-214AB, SMC K = A FUR SMCJ38A STM vs V _{BR} (I _T = 1.0 mA) = 33.30 42.40 B, V _{BM} = 20.0 B, I _{bp} = 26.0 A DC-214AB, SMC K = A FUR SMCJ38A STM vs V _{BR} (I _T = 1.0 mA) = 33.30 42.40 B, V _{BM} = 20.0 B, I _{bp} = 26.1 A DC-214AB, SMC K = A FUR SMCJ39A STM vs V _{BR} (I _T = 1.0 mA) = 36.70 42.20 B, V _{BM} = 20.0 B, I _{bp} = 26.1 A DC-214AB, SMC K = A FUR SMCJ48A STM vs V _{BR} (I _T = 1.0 mA) = 36.70 10.10 B, V _{BM} = 40.0 B, I _{bp} = 26.1 A DC-214AB, SMC K = A FUR SMCJ48A STM vs V _{BR} (I _T = 1.0 mA) = 36.30 61.30 B, V _{BM} = 40.0 B, I _{bp} = 24.4 DC-214AB, SMC K = A FUR SMCJ48A STM vs V _{BR} (I _T = 1.0 mA) = 36.30 61.30 B, V _{BM} = 48.0 B, I _{bp} = 19.4 A DC-214AB, SMC K = A FUR SMCJ48A STM vs V _{BR} (I _T = 1.0 mA) = 36.30 61.30 B, V _{BM} = 40.0 B, I _{bp} = 19.4 A DC-214AB, SMC K = A FUR SMCJ48A STM vs V _{BR} (I _T = 1.0 mA) = 36.30 61.30 B, V _{BM} = 40.0 B, I _{bp} = 19.4 A DC-214AB, SMC K = A FUR SMCJ48A STM vs V _{BR} (I _T = 1.0 mA) = 36.30 61.30	FUC	SMCJ6.5A	STM	VS	V _{BR} (I _T = 10.0 mA) = 7.228.30 B; V _{WM} = 6.5 B; I _{PP} = 133.9 A	DO-214AB, SMC	K•A
FUH SMCJ12A STM V V _{BE} (I ; = 1 0 MA) = 13.3015.30B, V _{WM} = 12 0.B, I _{PO} = 75.3A DO-2 14AB, SMC K = A FUI SMCJ13A STM V _{BE} (I ; = 1 0 MA) = 14.4016.50B, V _{WM} = 13.0B, I _{PO} = 69.7A DO-2 14AB, SMC K = A FUI SMCJ15A STM V _{BE} (I ; = 1 0 MA) = 16.70192.0B, V _{WM} = 13.0B, I _{PO} = 61.5A DO-2 14AB, SMC K = A FUI SMCJ16A STM V _{BE} (I ; = 1 0 MA) = 20.0023.30B, V _{WM} = 13.0B, I _{PO} = 51.4A DO-2 14AB, SMC K = A FUI SMCJ20A STM V _{BE} (I ; = 1 0 MA) = 22.2028.10B, I _{VWM} = 12.0B, I _{PO} = 541.9A DO-2 14AB, SMC K = A FUI SMCJ20A STM V _{BE} (I ; = 1 0 MA) = 24.2028.00B, V _{WM} = 20.0B, I _{PO} = 38.6A DO-2 14AB, SMC K = A FUI SMCJ26A STM V _{BE} (I ; = 1 0 MA) = 26.7030.70B, V _{WM} = 24.0B, I _{PO} = 33.6A DO-2 14AB, SMC K = A FUI SMCJ26A STM V _{BE} (I ; = 1 0 MA) = 26.7030.70B, V _{WM} = 24.0B, I _{PO} = 33.6A DO-2 14AB, SMC K = A FUI SMCJ26A STM V _{BE} (I ; = 1 0 MA) = 33.1035.80B, V _{WM} = 26.0B, I _{PO} = 33.0A DO-2 14AB, SMC K = A FUI SMCJ30A STM V _{BE} (I ; = 1 0 MA) = 33.1042.40B, V _{WM} = 30.0B, I _{PO} = 26.0A DO-2 14AB, SMC K = A FUI SMCJ30A STM V _{BE} (I ; = 1 0 MA) = 33.0042.40B, V _{WM} = 30.0B, I _{PO} = 26.0A DO-2 14AB, SMC K = A FUI SMCJ30A STM V _{BE} (I ; = 1 0 MA) = 33.0042.40B, V _{WM} = 30.0B, I _{PO} = 26.0A DO-2 14AB, SMC K = A FUI SMCJ30A STM V _{BE} (I ; = 1 0 MA) = 33.0042.40B, V _{WM} = 30.0B, I _{PO} = 26.0A DO-2 14AB, SMC K = A FUI SMCJ40A STM V _{BE} (I ; = 1 0 MA) = 33.0061.30B, V _{WM} = 40.0B, I _{PO} = 26.2A DO-2 14AB, SMC K = A FUI SMCJ48A STM V _{BE} (I ; = 1 0 MA) = 33.0061.30B, V _{WM} = 40.0B, I _{PO} = 26.2A DO-2 14AB, SMC K = A FUI SMCJ48A STM V _{BE} (I ; = 1 0 MA) = 33.0061.30B, V _{WM} = 40.0B, I _{PO} = 26.0A DO-2 14AB, SMC K = A FUI SMCJ48A STM V _{BE} (I ; = 1 0 MA) = 33.0061.30B, V _{WM} = 40.0B, I _{PO} = 26.0A DO-2 14AB, SMC K = A FUI SMCJ48A STM V _{BE} (I ; = 1 0 MA) = 33.0061.30B, V _{WM}	FUD	SMCJ8.5A	STM	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 9.4410.82 \text{ B}; V_{WM} = 8.5 \text{ B}; I_{pp} = 104.2 \text{ A}$	DO-214AB, SMC	K•A
FUI SMCJ13A STM V _{BR} (I ₁ = 1.0 мA) = 14.4016.50 B, V _{MM} = 13.0 B, I _{pp} = 69.7 A DC-214AB, SMC K + A FUJ SMCJ15A STM VS V _{BR} (I ₁ = 1.0 mA) = 16.7019.20 B, V _{MM} = 13.0 B, I _{pp} = 61.5 A DC-214AB, SMC K + A FUIL SMCJ18A STM VS V _{BR} (I ₁ = 1.0 mA) = 20.0023.30 B, V _{MM} = 18.0 B, I _{pp} = 51.4 A DC-214AB, SMC K + A FUM SMCJ20A STM VS V _{BR} (I ₁ = 1.0 mA) = 22.0.2020.10 B, V _{MM} = 20.0 B, I _{pp} = 41.9 A DC-214AB, SMC K + A FUN SMCJ22A STM VS V _{BR} (I ₁ = 1.0 mA) = 22.0.200020.30.70 B, V _{MM} = 20.0 B, I _{pp} = 33.6 A DC-214AB, SMC K + A FUN SMCJ24A STM VS V _{BR} (I ₁ = 1.0 mA) = 28.7030.70 B, V _{MM} = 20.0 B, I _{pp} = 33.6 A DC-214AB, SMC K + A FUN SMCJ24A STM VS V _{BR} (I ₁ = 1.0 mA) = 28.9038.80 B, V _{MM} = 20.0 B, I _{pp} = 33.0 A DC-214AB, SMC K + A FUN SMCJ24A STM VS V _{BR} (I ₁ = 1.0 mA) = 30.0.20.80 B, V _{MM} = 20.0 B, I _{pp} = 30.0 A DC-214AB, SMC K + A FUN SMCJ26A STM VS V _{BR} (I ₁ = 1.0 mA) = 33.0.42.40 B, V _{MM} = 30.0 B, I _{pp} = 20.0 A DC-214AB, SMC K + A FUN SMCJ36A STM VS V _{BR} (I ₁ = 1.0 mA) = 33.0.42.40 B, V _{MM} = 30.0 B, I _{pp} = 20.0 A DC-214AB, SMC K + A FUN SMCJ36A STM VS V _{BR} (I ₁ = 1.0 mA) = 36.7042.20 B, V _{MM} = 30.0 B, I _{pp} = 20.0 A DC-214AB, SMC K + A FUN SMCJ36A STM VS V _{BR} (I ₁ = 1.0 mA) = 36.7042.20 B, V _{MM} = 30.0 B, I _{pp} = 20.0 A DC-214AB, SMC K + A FUN SMCJ36A STM VS V _{BR} (I ₁ = 1.0 mA) = 36.7042.20 B, V _{MM} = 30.0 B, I _{pp} = 20.0 A DC-214AB, SMC K + A FUN SMCJ36A STM VS V _{BR} (I ₁ = 1.0 mA) = 36.7012.20 B, V _{MM} = 30.0 B, I _{pp} = 20.0 A DC-214AB, SMC K + A FUN SMCJ36A STM VS V _{BR} (I ₁ = 1.0 mA) = 36.7012.10 B, V _{MM} = 30.0 B, I _{pp} = 20.0 A DC-214AB, SMC K + A FUN SMCJ36A STM VS V _{BR} (I ₁ = 1.0 mA) = 36.7012.10 B, V _{MM} = 30.0 B, I _{pp} = 20.0 A DC-214AB, SMC K + A FUN SMCJ36A STM VS V _{BR} (I ₁ = 1.0 mA) = 36.7012.10 B, V _{MM} = 30.0 B, I _{pp} = 20.0 A DC-214AB, SMC K + A FUN SMCJ36A STM VS V _{BR} (I ₁ = 1.0 mA) = 36.7012.10 B, V _{MM} = 30.0 B, I _{pp} = 20.0 A DC-214AB, SMC K + A FUN SMCJ36A STM VS V _{BR} (I ₁ = 1.0 mA) = 36.7012.10 B, V _{MM}	FUF	SMCJ10A	STM	VS	V _{BR} (I _T = 1.0 mA) = 11.1012.80 B; V _{WM} = 10.0 B; I _{PP} = 88.2 A	DO-214AB, SMC	K•A
FUL SMCJ18A STM vs V _{BR} (I _T = 1 0 мA) = 16.7019.20 B, V _{WM} = 15.0 B, I _{DP} = 61.5 A DC-214AB, SMC K = A FUL SMCJ18A STM vs V _{BR} (I _T = 1 0 mA) = 20.0023.30 B, V _{WM} = 10.0 B, I _{DP} = 51.4 A DC-214AB, SMC K = A FUM SMCJ20A STM vs V _{BR} (I _T = 1 0 mA) = 22.00281.0 B, V _{WM} = 20.0 B, I _{DP} = 41.9 A DC-214AB, SMC K = A FUM SMCJ20A STM vs V _{BR} (I _T = 1 0 mA) = 24.00280.0 B, V _{WM} = 20.0 B, I _{DP} = 36.6 A DC-214AB, SMC K = A FUD SMCJ20A STM vs V _{BR} (I _T = 1 0 mA) = 26.7030.70 B, V _{WM} = 20.0 B, I _{DP} = 38.6 A DC-214AB, SMC K = A FUD SMCJ20A STM vs V _{BR} (I _T = 1 0 mA) = 28.9036.0 B, V _{WM} = 20.0 B, I _{DP} = 32.2 A DC-214AB, SMC K = A FUR SMCJ20A STM vs V _{BR} (I _T = 1 0 mA) = 33.3042.40 B, V _{WM} = 20.0 B, I _{DP} = 30.0 A DC-214AB, SMC K = A FUR SMCJ30A STM vs V _{BR} (I _T = 1 0 mA) = 33.3042.40 B, V _{WM} = 20.0 B, I _{DP} = 26.0 A DC-214AB, SMC K = A FUR SMCJ30A STM vs V _{BR} (I _T = 1 0 mA) = 36.7042.0 B, V _{WM} = 30.0 B, I _{DP} = 26.1 A DC-214AB, SMC K = A FUR SMCJ30A STM vs V _{BR} (I _T = 1 0 mA) = 36.7042.0 B, V _{WM} = 30.0 B, I _{DP} = 26.1 A DC-214AB, SMC K = A FUR SMCJ30A STM vs V _{BR} (I _T = 1 0 mA) = 36.7042.0 B, V _{WM} = 30.0 B, I _{DP} = 26.1 A DC-214AB, SMC K = A FUR SMCJ30A STM vs V _{BR} (I _T = 1 0 mA) = 36.7042.0 B, V _{WM} = 30.0 B, I _{DP} = 26.1 A DC-214AB, SMC K = A FUR SMCJ30A STM vs V _{BR} (I _T = 1 0 mA) = 36.3061.30 B, V _{WM} = 40.0 B, I _{DP} = 19.4 A DC-214AB, SMC K = A FUR SMCJ30A STM vs V _{BR} (I _T = 1 0 mA) = 63.3061.30 B, V _{WM} = 40.0 B, I _{DP} = 19.4 A DC-214AB, SMC K = A FUR SMCJ30A STM vs V _{BR} (I _T = 1 0 mA) = 63.3061.30 B, V _{WM} = 40.0 B, I _{DP} = 19.4 A DC-214AB, SMC K = A FUR SMCJ30A STM vs V _{BR} (I _T = 1 0 mA) = 63.3061.30 B, V _{WM} = 40.0 B, I _{DP} = 19.4 A DC-214AB, SMC K = A FUR SMCJ30A STM vs V _{BR} (I _T = 1 0 mA) = 63.3061.30 B, V _{WM} = 40.0 B, I _{DP} = 19.4 A DC-214AB, SMC K = A FUR SMCJ30A STM vs V _{BR} (I _T = 1 0 mA) = 63.3061.30 B, V _{WM} = 40.0 B, I _{DP} = 19.4 A DC-214AB, SMC K = A FUR SMCJ30A STM vs V _{BR} (I _T = 1 0 mA) = 63.3061.30 B, V _{WM} = 40.0	FUH	SMCJ12A	STM	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 13.3015.30 \text{ B}; V_{WM} = 12.0 \text{ B}; I_{PP} = 75.3 \text{ A}$	DO-214AB, SMC	K•A
FUL SMCJ20A STM vs V _{BR} (I ₁ =1.0 мA)=22.0023.00 B, V _{MM} =18.0 B, I ₅₀ =51.4 A DC-214AB, SMC K ► A FUM SMCJ20A STM vs V _{BR} (I ₁ =1.0 mA)=22.0028.10 B, V _{MM} =20.0 B, I ₅₀ =41.9 A DC-214AB, SMC K ► A FUD SMCJ22A STM vs V _{BR} (I ₁ =1.0 mA)=22.4 C 28.0 DB, V _{MM} =20.0 B, I ₅₀ =42.2 A DC-214AB, SMC K ► A FUD SMCJ26A STM vs V _{BR} (I ₁ =1.0 mA)=24.0 28.0 DB, V _{MM} =20.0 B, I ₅₀ =38.6 A DC-214AB, SMC K ► A FUD SMCJ26A STM vs V _{BR} (I ₁ =1.0 mA)=28.9036.80 B, V _{MM} =20.0 B, I ₅₀ =32.2 A DC-214AB, SMC K ► A FUD SMCJ26A STM vs V _{BR} (I ₁ =1.0 mA)=33.0 42.40 B, V _{MM} =20.0 B, I ₅₀ =30.0 A DC-214AB, SMC K ► A FUD SMCJ30A STM vs V _{BR} (I ₁ =1.0 mA)=33.0 42.40 B, V _{MM} =30.0 B, I ₅₀ =28.0 A DC-214AB, SMC K ► A FUL SMCJ30A STM vs V _{BR} (I ₁ =1.0 mA)=36.70 42.20 B, V _{MM} =30.0 B, I ₅₀ =28.1 A DC-214AB, SMC K ► A FUL SMCJ40A STM vs V _{BR} (I ₁ =1.0 mA)=67.0 42.20 B, V _{MM} =30.0 B, I ₅₀ =28.1 A DC-214AB, SMC K ► A FUL SMCJ40A STM vs V _{BR} (I ₁ =1.0 mA)=67.0 42.20 B, V _{MM} =30.0 B, I ₅₀ =28.1 A DC-214AB, SMC K ► A FUL SMCJ40A STM vs V _{BR} (I ₁ =1.0 mA)=63.00 61.30 B, V _{MM} =48.0 B, I ₅₀ =19.4 A DC-214AB, SMC K ► A FUL SMCJ48A STM vs V _{BR} (I ₁ =1.0 mA)=63.00 61.30 B, V _{MM} =48.0 B, I ₅₀ =19.4 A DC-214AB, SMC K ► A FUL SMCJ48A STM vs V _{BR} (I ₁ =1.0 mA)=63.00 61.30 B, V _{MM} =48.0 B, I ₅₀ =19.4 A DC-214AB, SMC K ► A FUL SMCJ48A STM vs V _{BR} (I ₁ =1.0 mA)=63.00 61.30 B, V _{MM} =48.0 B, I ₅₀ =19.4 A DC-214AB, SMC K ► A FUL SMCJ48A STM vs V _{BR} (I ₁ =1.0 mA)=63.00 61.30 B, V _{MM} =48.0 B, I ₅₀ =19.4 A DC-214AB, SMC K ► A FUL SMCJ48A STM vs V _{BR} (I ₁ =1.0 mA)=63.00 61.30 B, V _{MM} =48.0 B, I ₅₀ =19.4 A DC-214AB, SMC K ► A FUL SMCJ48A STM vs V _{BR} (I ₁ =1.0 mA)=63.00 61.30 B, V _{MM} =48.0 B, I ₅₀ =19.4 A DC-214AB, SMC K ► A FUL SMCJ48A STM vs V _{BR} (I ₁ =1.0 mA)=63.00 61.30 B, V _{MM} =48.0 B, I ₅₀ =19.4 A DC-214AB, SMC K ► A FUL SMCJ48A STM vs V _{BR} (I ₁ =1.0 mA)=63.00 61.30 B, V _{MM} =48.0 B, I ₅₀ =19.4 A DC-214AB, SMC K ► A FUL SMCJ48A STM vs V _{BR} (I ₁ =1.0 mA)=63.00 61.30 B, V _{MM} =48.0 B, I ₅₀ =19.4 A DC-214AB,	FUI	SMCJ13A	STM		V _{BB} (I _T = 1.0 mA) = 14.4016.50 B; V _{WM} = 13.0 B; I _{PP} = 69.7 A	DO-214AB, SMC	K•A
FUM SMCJ20A STM vs V _{BR} (I _T = 1.0 мA) = 22.2028.10 B, V _{MM} = 20.0 B, I ₅₀ = 41.9 A DC-214AB, SMC K = A FUN SMCJ22A STM vs V _{BR} (I _T = 1.0 мA) = 22.2028.0 B, V _{MM} = 22.0 B, I ₅₀ = 42.2 A DC-214AB, SMC K = A FUD SMCJ26A STM vs V _{BR} (I _T = 1.0 мA) = 26.7030.70 B, V _{MM} = 24.0 B, I ₅₀ = 38.6 A DC-214AB, SMC K = A FUD SMCJ26A STM vs V _{BR} (I _T = 1.0 мA) = 26.7030.70 B, V _{MM} = 24.0 B, I ₅₀ = 33.6 A DC-214AB, SMC K = A FUD SMCJ26A STM vs V _{BR} (I _T = 1.0 мA) = 31.1035.80 B, V _{MM} = 28.0 B, I ₅₀ = 33.0 A DC-214AB, SMC K = A FUB SMCJ30A STM vs V _{BR} (I _T = 1.0 мA) = 31.1035.80 B, V _{MM} = 30.0 B, I ₅₀ = 28.0 A DC-214AB, SMC K = A FUB SMCJ30A STM vs V _{BR} (I _T = 1.0 мA) = 33.0 A, 24.20 B, V _{MM} = 30.0 B, I ₅₀ = 28.1 A DC-214AB, SMC K = A FUB SMCJ30A STM vs V _{BR} (I _T = 1.0 мA) = 67.042.20 B, V _{MM} = 30.0 B, I ₅₀ = 28.1 A DC-214AB, SMC K = A FUB SMCJ40A STM vs V _{BR} (I _T = 1.0 мA) = 67.042.20 B, V _{MM} = 30.0 B, I ₅₀ = 28.1 A DC-214AB, SMC K = A FUB SMCJ40A STM vs V _{BR} (I _T = 1.0 мA) = 63.3061.30 B, V _{MM} = 48.0 B, I ₅₀ = 19.4 A DC-214AB, SMC K = A FUB SMCJ48A STM vs V _{BR} (I _T = 1.0 мA) = 63.3061.30 B, V _{MM} = 48.0 B, I ₅₀ = 19.4 A DC-214AB, SMC K = A FUB SMCJ48A STM vs V _{BR} (I _T = 1.0 мA) = 63.3061.30 B, V _{MM} = 48.0 B, I ₅₀ = 19.4 A DC-214AB, SMC K = A FUB SMCJ48A STM vs V _{BR} (I _T = 1.0 мA) = 63.3061.30 B, V _{MM} = 40.8 B, I ₅₀ = 19.4 A DC-214AB, SMC K = A FUB SMCJ48A STM vs V _{BR} (I _T = 1.0 мA) = 63.3061.30 B, V _{MM} = 40.8 B, I ₅₀ = 19.4 A DC-214AB, SMC K = A FUB SMCJ48A STM vs V _{BR} (I _T = 1.0 мA) = 63.3061.30 B, V _{MM} = 40.8 B, I ₅₀ = 19.4 A DC-214AB, SMC K = A FUB SMCJ48A STM vs V _{BR} (I _T = 1.0 мA) = 63.3061.30 B, V _{MM} = 40.8 B, I ₅₀ = 19.4 A DC-214AB, SMC K = A FUB SMCJ48A STM vs V _{BR} (I _T = 1.0 мA) = 63.3061.30 B, V _{MM} = 40.8 B, I ₅₀ = 19.4 A DC-214AB, SMC K = A FUB SMCJ48A STM vs V _{BR} (I _T = 1.0 MA) = 63.3061.30 B, V _{MM} = 40.8 B, I ₅₀ = 19.4 A DC-214AB, SMC K = A FUB SMCJ48A STM vs V _{BR} (I _T = 1.0 MA) = 63.3061.30 B, V _{MM} =	FUJ	SMCJ15A	STM	VS	V _{BR} (I _T = 1.0 mA) = 16.7019.20 B; V _{WM} = 15.0B; I _{PP} = 61.5 A	DO-214AB, SMC	K•A
FUN SMCJ22A STM vs V _{SR} (t ₁ = 1.0 mA) = 24.4028.00 B, V _{6m} = 22.0 B, t ₅ = 42.2 A DC-214AB, SMC K + A FUO SMCJ24A STM vs V _{SR} (t ₁ = 1.0 mA) = 26.7030.70 B, V _{6m} = 24.00 B, t ₅ = 38.6 A DC-214AB, SMC K + A FUD SMCJ26A STM vs V _{SR} (t ₁ = 1.0 mA) = 28.9038.0 B, V _{6m} = 26.0 B, t ₅ = 32.2 A DC-214AB, SMC K + A FUD SMCJ26A STM vs V _{SR} (t ₁ = 1.0 mA) = 38.902 M ₅ = 28.00. B, t ₅ = 30.0 A DC-214AB, SMC K + A FUB SMCJ30A STM vs V _{SR} (t ₁ = 1.0 mA) = 33.042.40 B, V _{6m} = 30.0 B, t ₅ = 20.0 A DC-214AB, SMC K + A FUS SMCJ30A STM vs V _{SR} (t ₁ = 1.0 mA) = 36.7042.0 B, V _{6m} = 30.0 B, t ₅ = 26.1 A DC-214AB, SMC K + A FUD SMCJ40A STM vs V _{SR} (t ₁ = 1.0 mA) = 36.7042.0 B, V _{6m} = 30.0 B, t ₅ = 26.1 A DC-214AB, SMC K + A FUU SMCJ40A STM vs V _{SR} (t ₁ = 1.0 mA) = 36.7010 B, V _{6m} = 40.0 B, t ₅ = 22.2 A DC-214AB, SMC K + A FUU SMCJ40A STM vs V _{SR} (t ₁ = 1.0 mA) = 53.3061.30 B, V _{6m} = 40.0 B, t ₅ = 19.4 A DC-214AB, SMC K + A FUU SMCJ48A STM vs V _{SR} (t ₁ = 1.0 mA) = 53.3061.30 B, V _{6m} = 40.0 B, t ₅ = 19.4 A DC-214AB, SMC K + A FUU SMCJ48A STM vs V _{SR} (t ₁ = 1.0 mA) = 53.3061.30 B, V _{6m} = 40.0 B, t ₅ = 19.4 A DC-214AB, SMC K + A FUU SMCJ48A STM vs V _{SR} (t ₁ = 1.0 mA) = 53.3061.30 B, V _{6m} = 40.0 B, t ₅ = 19.4 A DC-214AB, SMC K + A FUU SMCJ48A STM vs V _{SR} (t ₁ = 1.0 mA) = 53.3061.30 B, V _{6m} = 40.0 B, t ₅ = 19.4 A DC-214AB, SMC K + A FUU SMCJ48A STM vs V _{SR} (t ₁ = 1.0 mA) = 53.3061.30 B, V _{6m} = 40.0 B, t ₅ = 19.4 A DC-214AB, SMC K + A FUU SMCJ48A STM vs V _{SR} (t ₁ = 1.0 mA) = 53.3061.30 B, V _{6m} = 40.0 B, t ₅ = 19.4 A DC-214AB, SMC K + A FUU SMCJ48A STM vs V _{5R} (t ₁ = 1.0 mA) = 53.3061.30 B, V _{6m} = 40.0 B, t ₅ = 19.4 A DC-214AB, SMC K + A FUU SMCJ48A STM vs V _{5R} (t ₁ = 1.0 mA) = 53.3061.30 B, V _{6m} = 40.0 B, t ₅ = 19.4 A DC-214AB, SMC K + A FUU SMCJ48A STM vs V _{5R} (t ₁ = 1.0 mA) = 53.0061.30 B, V _{6m} = 40.0 B, t ₅ = 19.4 A DC-214AB, SMC K + A FUU SMCJ48A STM vs V _{5R} (t ₁ = 1.0 mA) = 53.0061.30 B, V _{6m} = 40.0 B, t ₅ = 10.0 C, t ₅ =	FUL	SMCJ18A	STM	VS	V _{BR} (I _T = 1.0 mA) = 20.0023.30 B; V _{MM} = 18.0 B; I _{PP} = 51.4 A	DO-214AB, SMC	K•A
FUID SMCJ24A STM VS V _{BE} (I ₇ = 1.0 мA) = 26.7030.70 B, V _{WM} = 24.0 B, I _{PP} = 38.6 A DO-214AB, SMC K • A FUP SMCJ26A STM VS V _{BE} (I ₇ = 1.0 мA) = 28.9036.80 B, V _{WM} = 26.0 B, I _{PP} = 32.2 A DO-214AB, SMC K • A FUR SMCJ26A STM VS V _{BE} (I ₇ = 1.0 мA) = 33.3042.40 B, V _{WM} = 20.0 B, I _{PP} = 33.0 A DO-214AB, SMC K • A FUB SMCJ30A STM VS V _{BE} (I ₇ = 1.0 мA) = 33.3042.40 B, V _{WM} = 30.0 B, I _{PP} = 28.1 A DO-214AB, SMC K • A FUB SMCJ30A STM VS V _{BE} (I ₇ = 1.0 мA) = 33.0042.40 B, V _{WM} = 30.0 B, I _{PP} = 28.1 A DO-214AB, SMC K • A FUB SMCJ30A STM VS V _{BE} (I ₇ = 1.0 мA) = 44.4051.10 B, V _{WM} = 40.0 B, I _{PP} = 22.2 A DO-214AB, SMC K • A FUB SMCJ40A STM VS V _{BE} (I ₇ = 1.0 мA) = 33.0061.30 B, V _{WM} = 44.0 B, I _{PP} = 19.4 A DO-214AB, SMC K • A FUB SMCJ48A STM VS V _{BE} (I ₇ = 1.0 мA) = 53.3061.30 B, V _{WM} = 48.0 B, I _{PP} = 19.4 A DO-214AB, SMC K • A FUB SMCJ48A STM VS V _{BE} (I ₇ = 1.0 мA) = 53.3061.30 B, V _{WM} = 48.0 B, I _{PP} = 19.4 A DO-214AB, SMC K • A FUB SMCJ48A STM VS V _{BE} (I ₇ = 1.0 мA) = 53.3061.30 B, V _{WM} = 48.0 B, I _{PP} = 19.4 A DO-214AB, SMC K • A FUB SMCJ48A STM VS V _{BE} (I ₇ = 1.0 мA) = 53.3061.30 B, V _{WM} = 48.0 B, I _{PP} = 19.4 A DO-214AB, SMC K • A FUB SMCJ48A STM VS V _{BE} (I ₇ = 1.0 мA) = 53.3061.30 B, V _{WM} = 48.0 B, I _{PP} = 19.4 A DO-214AB, SMC K • A FUB SMCJ48A STM VS V _{BE} (I ₇ = 1.0 мA) = 53.3061.30 B, V _{WM} = 48.0 B, I _{PP} = 19.4 A DO-214AB, SMC K • A FUB SMCJ48A STM VS V _{BE} (I ₇ = 1.0 мA) = 53.3061.30 B, V _{WM} = 48.0 B, I _{PP} = 19.4 A DO-214AB, SMC K • A FUB SMCJ48A STM VS V _{BE} (I ₇ = 1.0 MA) = 53.3061.30 B, V _{WM} = 48.0 B, I _{PP} = 19.4 A DO-214AB, SMC K • A FUB SMCJ48A STM VS V _{BE} (I ₇ = 1.0 MA) = 53.3061.30 B, V _{WM} = 48.0 B, I _{PP} = 19.4 A DO-214AB, SMC K • A FUB SMCJ48A STM VS V _{BE} (I ₇ = 1.0 MA) = 44.00.51.10 B, V _{WM} = 44.00.51.10	FUM	SMCJ20A	STM	VS	V _{BR} (I _T = 1.0 mA) = 22.2028.10 B; V _{WM} = 20.0B; I _{PP} = 41.9 A	DO-214AB, SMC	K•A
FUP SMCJ26A STM vs V _{Br} (I ₇ = 1.0 мA) = 28.9036.80 B, V _{WM} = 26.0B, I ₅₀ = 32.2 A DO-214AB, SMC K ► A FUQ SMCJ28A STM vs V _{gr} (I ₇ = 1.0 мA) = 31.1035.80 B, V _{WM} = 28.0 B, I ₅₀ = 28.0 A DO-214AB, SMC K ► A FUB SMCJ30A STM vs V _{gr} (I ₇ = 1.0 мA) = 33.3042.40 B, V _{WM} = 30.0 B, I ₅₀ = 28.1 A DO-214AB, SMC K ► A FUB SMCJ30A STM vs V _{gr} (I ₇ = 1.0 мA) = 67.042.20 B, V _{WM} = 30.0 B, I ₅₀ = 28.1 A DO-214AB, SMC K ► A FUB SMCJ40A STM vs V _{gr} (I ₇ = 1.0 мA) = 64.051.10 B, V _{WM} = 40.0B, I ₅₀ = 23.2 A DO-214AB, SMC K ► A FUW SMCJ48A STM vs V _{gr} (I ₇ = 1.0 мA) = 63.3061.30 B, V _{WM} = 48.0 B, I ₅₀ = 19.4 A DO-214AB, SMC K ► A	FUN	SMCJ22A	STM	VS	V _{BR} (I _T = 1.0 mA) = 24.4028.00 B; V _{WM} = 22.0B; I _{PP} = 42.2 A	DO-214AB, SMC	K•A
FUIQ SMC,128A STM vs V _{BB} (l ₁ = 1 0 mA) = 31.1035.80 B, V _{MM} = 28.0 B, I ₅₀ = 33.0 A DO-214AB, SMC K = A FUIS SMC,130A STM vs V _{BB} (l ₁ = 1 0 mA) = 33.0.4.24 0 B, V _{MM} = 30.0 B, I ₅₀ = 28.0 A DO-214AB, SMC K = A FUIS SMC,133A STM vs V _{BB} (l ₁ = 1 0 mA) = 67.042.20 B, V _{MM} = 30.0 B, I ₅₀ = 28.1 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 67.042.20 B, V _{MM} = 30.0 B, I ₅₀ = 28.1 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 63.0061.30 B, V _{MM} = 40.0 B, I ₅₀ = 19.4 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 63.3061.30 B, V _{MM} = 40.0 B, I ₅₀ = 19.4 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 63.3061.30 B, V _{MM} = 40.0 B, I ₅₀ = 19.4 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 63.3061.30 B, V _{MM} = 40.0 B, I ₅₀ = 19.4 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 63.3061.30 B, V _{MM} = 40.0 B, I ₅₀ = 19.4 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 63.3061.30 B, V _{MM} = 40.0 B, I ₅₀ = 19.4 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 63.3061.30 B, V _{MM} = 40.0 B, I ₅₀ = 19.4 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 63.3061.30 B, V _{MM} = 40.0 B, I ₅₀ = 19.4 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 63.3061.30 B, V _{MM} = 40.0 B, I ₅₀ = 19.4 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 63.3061.30 B, V _{MM} = 40.0 B, I ₅₀ = 19.4 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 63.3061.30 B, V _{MM} = 40.0 B, I ₅₀ = 19.4 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 63.3061.30 B, V _{MM} = 40.0 B, I ₅₀ = 19.4 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 63.3061.30 B, V _{MM} = 40.0 B, I ₅₀ = 13.30 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁ = 1 0 mA) = 63.3061.30 B, V _{MM} = 40.0 B, I ₅₀ = 13.30 A DO-214AB, SMC K = A FUIU SMC,140A STM vs V _{BB} (l ₁	FUO	SMCJ24A	STM	VS		DO-214AB, SMC	K•A
FUQ SMCJ28A STM vs V _{BR} (I ₇ =1.0 мA)=31.1035.80 B, V _{ew} = 28.0 B, I ₅₉ =33.0 A DC-214AB, SMC K ◆ A FUR SMCJ30A STM vs V _{BR} (I ₇ =1.0 mA)=33.0042.40 B, V _{ew} = 30.0 B, I ₅₉ =28.0 A DC-214AB, SMC K ◆ A FUU SMCJ40A STM vs V _{BR} (I ₇ =1.0 mA)=67.042.20 B, V _{ew} = 30.0 B, I ₅₉ =28.1 A DC-214AB, SMC K ◆ A FUU SMCJ40A STM vs V _{BR} (I ₇ =1.0 mA)=67.042.20 B, V _{ew} = 30.0 B, I ₅₉ =28.1 A DC-214AB, SMC K ◆ A FUW SMCJ40A STM vs V _{BR} (I ₇ =1.0 mA)=63.0061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I ₅₉ =19.4 A DC-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ =1.0 mA)=63.3061.30 B, V _{ew} = 48.0 B, I	FUP	SMCJ26A	STM	٧S	V _{BR} (I _T = 1.0 MA) = 28.9036.80 B; V _{WM} = 26.0 B; I _{PP} = 32.2 A	DO-214AB, SMC	K•A
FUR SMCJ30A STM vs V _{GR} (1,=1.0 mA)=33.3042.40 B, V _{ew} =30.0 B, t _p =28.0 A DC-214AB, SMC K + A FUS SMCJ33A STM vs V _{GR} (1,=1.0 mA)=36.7042.20 B, V _{ew} =30.0 B, t _p =28.1 A DC-214AB, SMC K + A FUU SMCJ40A STM vs V _{GR} (1,=1.0 mA)=36.7042.20 B, V _{ew} =30.0 B, t _p =28.1 A DC-214AB, SMC K + A FUU SMCJ40A STM vs V _{GR} (1,=1.0 mA)=45.0 S, 10.0 B, V _{ew} =40.0 B, t _p =22.2 A DC-214AB, SMC K + A FUW SMCJ48A STM vs V _{GR} (1,=1.0 mA)=53.3061.30 B, V _{ew} =40.0 B, t _p =19.4 A DC-214AB, SMC K + A DC-214AB, SMC K + A SMC K + A SMCJ48A SMC K	FUQ	SMCJ28A	STM	VS		DO-214AB, SMC	K•A
FUS SMCJ33A STM vs V _{BR} (I ₇ = 1.0 мA) = 36.7042.20 B, V _{MM} = 33.0 B, I _{PP} = 28.1 A DO-214AB, SMC K ◆ A FUU SMCJ40A STM vs V _{BR} (I ₇ = 1.0 мA) = 44.4051.10 B, V _{MM} = 40.0 B, I _{PP} = 23.2 A DO-214AB, SMC K ◆ A FUW SMCJ48A STM vs V _{BR} (I ₇ = 1.0 мA) = 53.3061.30 B, V _{MM} = 48.0 B, I _{PP} = 19.4 A DO-214AB, SMC K ◆ A	FUR	SMCJ30A	STM	VS		DO-214AB, SMC	K•A
FUU SMC.449A STM vs V _{SR} (1 ₇ = 1.0 мA) = 44.4051.10B; V _{sM} = 40.0B; I _{bp} = 23.2A DO-214AB, SMC K ◆ A FUW SMC.448A STM vs V _{SR} (1 ₇ = 1.0 мA) = 53.3061.30B; V _{sM} = 48.0B; I _{bp} = 19.4A DO-214AB, SMC K ◆ A	FUS	SMCJ33A	STM	VS		DO-214AB, SMC	K•A
FUW SMCJ48A STM vs V _{BR} (I _T = 1.0 MA) = 53.3061.30 B; V _{MM} = 48.0 B; I _{PP} = 19.4 A DO-214AB; SMC K • A	FUU	SMCJ40A	STM	VS		DO-214AB, SMC	K∙A
	FUW	SMCJ48A	STM	VS		DO-214AB, SMC	K•A
	FUZ	SMCJ58A	STM	VS		DO-214AB, SMC	K•A



Код	Типономинал	Б	Φ	Особенности	Корпус	Ц: 1•2
GA	GF1A	VISH	dr	V _B < 50 B; I _F < 1 A; V _F (I _F = 1 A) < 1.1 B	DO-214BA	K∙A
GA	GF1A	GS	dr	V _R < 50 B; I _F < 1 A; V _F (I _F = 1 A) < 1.1 B	DO-214BA	K•A
GB	GF1B	VISH	dr	V _B <100 B; I _F <1 A; V _F (I _F =1 A)<1.1 B	DO-214BA	K•A
GB	GF1B	GS	dr	V _B <100 B; I _F <1 A; V _F (I _F =1 A)<1.1 B	DO-214BA	K•A
GBB	SMCJ70CA	STM	vs	V _{BR} (I _T = 1.0 mA) = 77.8089.50 B; V _{WM} = 70.0 B; I _{PP} = 13.3 A	DO-214AB, SMC	х∙х
GBCA	SMCJ60CA	STM	VS	V _{BR} (I _T = 1.0 mA) = 66.7076.70 B; V _{VM} = 60.0 B; I _{PP} = 15.5 A	DO-214AB, SMC	χ∙χ
GBE	SMCJ85CA	STM	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 94.40108.20 \text{ B}; V_{WM} = 85.0 \text{ B}; I_{PP} = 10.4 \text{ A}$	DO-214AB, SMC	х∙х
GBG	SMCJ100CA	STM	VS	V _{BR} (I _T = 1.0 mA) = 111.00141.00 B; V _{WM} = 100.0 B; I _{PP} = 8.4A	DO-214AB, SMC	х∙х
GBI	SMCJ130CA	STM	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 144.00182.50 \text{ B}; V_{WM} = 130.0 \text{ B}; I_{PP} = 6.5 \text{ A}$	DO-214AB, SMC	x•x
GBL	SMCJ154CA	STM	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 171 \text{ B}; V_{WM} = 154.0 \text{ B}; I_{PP} = 6.1 \text{ A}$	DO-214AB, SMC	х∙х
GBM	SMCJ170CA	STM	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 189.00217.50 \text{ B}; V_{WM} = 170.0 \text{ B}; I_{PP} = 5.5 \text{ A}$	DO-214AB, SMC	х•х
GBN	SMCJ188CA	STM	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 209 \text{ B}; V_{WM} = 188.0 \text{ B}; I_{PP} = 4.6 \text{ A}$	DO-214AB, SMC	х∙х
GD	GF1D	VISH	dr	V _B <200 B; I _F <1 A; V _F (I _F =1 A)<1.1 B	DO-214BA	K∙A
GD	GF1D	GS	dr	V _B <200 B; I _F <1 A; V _F (I _F =1 A)<1.1 B	DO-214BA	K∙A
GDD	SMCJ5.0	VISH	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.407.55 \text{ B}; V_{WM} = 5.0 \text{ B}; I_{pp} = 156.2 \text{ A}$	DO-214AB, SMC	K•A
GDE	1SMC5.0AT3	ON	vs	V _{BR} (I _T = 10.0 mA) = 6.47.0 B; V _{WM} = 9.2 B; I _{PP} = 163 A	DO-214AB, SMC	K∙A
GDE	SMCJ5.0A	VISH	٧S	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.407.25 \text{ B}; V_{WM} = 5.0 \text{ B}; I_{pp} = 163.0 \text{ A}$	DO-214AB, SMC	K∙A
GDF	SMCJ6.0	VISH	vs	V _{BR} (I _T = 10.0 mA) = 6.678.45 B; V _{WM} = 6.0 B; I _{pp} = 131.6 A	DO-214AB, SMC	K∙A
GDG	1SMC6.0AT3	ON	vs	V _{BR} (I _T = 10.0 mA) = 6.677.37 B; V _{WM} = 10.3 B; I _{PP} = 145.6 A	DO-214AB, SMC	K∙A
GDG	SMCJ6.0A	VISH	vs	V _{BR} (I _T = 10.0 mA) = 6.677.67 B; V _{WM} = 6.0 B; I _{pp} = 145.6 A	DO-214AB, SMC	K∙A
GDH	SMCJ6.5	VISH	vs	V _{BR} (I _T = 10.0 mA) = 7.229.14 B; V _{WM} = 6.5 B; I _{pp} = 122.0 A	DO-214AB, SMC	K•A
GDK	1SMC6.5AT3	ON	vs	V _{BR} (I _T = 10.0 mA) = 7.227.98 B; V _{WM} = 11.2 B; I _{PP} = 133.9 A	DO-214AB, SMC	K∙A
GDK	SMCJ6.5A	VISH	vs	V _{BR} (I _T = 10.0 mA) = 7.228.30 B; V _{WM} = 6.5 B; I _{PP} = 133.9 A	DO-214AB, SMC	K∙A
GDL	SMCJ7.0	VISH	vs	V _{BR} (I _T = 10.0 mA) = 7.789.86 B; V _{WM} = 7.0 B; I _{pp} = 112.8 A	DO-214AB, SMC	K∙A
GDM	1SMC7.0AT3	ON	vs	V _{BR} (I _T = 10.0 mA) = 7.788.6B; V _{WM} = 12B; I _{PP} = 125A	DO-214AB, SMC	K∙A
GDM	SMCJ7.0A	VISH	vs	V _{BR} (I _T = 10.0 mA) = 7.788.95 B; V _{WM} = 7.0 B; I _{pp} = 125.0 A	DO-214AB, SMC	K•A
GDN	SMCJ7.5	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 8.3310.80 \text{ B}; V_{WM} = 7.5 \text{ B}; I_{pp} = 104.9 \text{ A}$	DO-214AB, SMC	K∙A
GDP	1SMC7.5AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 8.339.21 B; V _{WM} = 12.9 B; I _{pp} = 116.3 A	DO-214AB, SMC	K∙A
GDP	SMCJ7.5A	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 8.339.58 \text{ B; } V_{WM} = 7.5 \text{ B; } I_{PP} = 116.3 \text{ A}$	DO-214AB, SMC	K∙A
GDQ	SMCJ8.0	VISH	vs	V _{BR} (I _T = 1.0 mA) = 8.8911.30 B; V _{WM} = 8.0 B; I _{PP} = 100.0 A	DO-214AB, SMC	K•A
GDR	1SMC8.0AT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 8.899.83 \text{ B}; V_{WM} = 13.6 \text{ B}; I_{pp} = 110.3 \text{ A}$	DO-214AB, SMC	K∙A
GDR	SMCJ8.0A	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 8.8910.23 \text{ B}; V_{WM} = 8.0 \text{ B}; I_{pp} = 110.3 \text{ A}$	DO-214AB, SMC	K∙A
GDS	SMCJ8.5	VISH	vs	V _{BR} (I _T = 1.0 mA) = 9.4411.92 B; V _{WM} = 8.5 B; I _{PP} = 94.3 A	DO-214AB, SMC	K∙A
GDT	1SMC8.5AT3	ON	νs	$V_{BR}(I_T = 1.0 \text{ mA}) = 9.4410.4 \text{ B; } V_{WM} = 14.4 \text{ B; } I_{pp} = 104.2 \text{ A}$	DO-214AB, SMC	K∙A
GDT	SMCJ8.5A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 9.4410.82 B; V _{WM} = 8.5 B; I _{pp} = 104.2 A	DO-214AB, SMC	K•A
GDU	SMCJ9.0	VISH	vs	V _{BR} (I _T = 1.0 mA) = 10.0012.80 B; V _{WM} = 9.0 B; I _{PP} = 88.7 A	DO-214AB, SMC	K•A
GDV	1SMC9.0AT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 1011.1 \text{ B}; V_{MM} = 15.4 \text{ B}; I_{PP} = 97.4 \text{ A}$	DO-214AB, SMC	K•A
GDV	SMCJ9.0A	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 10.0011.50 \text{ B}; V_{VMM} = 9.0 \text{ B}; I_{PP} = 97.4 \text{ A}$	DO-214AB, SMC	K•A
GDW	SMCJ10	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 11.1014.10 \text{ B}; V_{MM} = 10.0 \text{ B}; I_{pp} = 79.8 \text{ A}$	DO-214AB, SMC	K∙A
GDX	1SMC10AT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 11.112.3 \text{ B}; V_{WM} = 17 \text{ B}; I_{PP} = 88.2 \text{ A}$	DO-214AB, SMC	K•A
GDX	SMCJ10A	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 11.1012.80 \text{ B}; V_{MM} = 10.0 \text{ B}; I_{pp} = 88.2 \text{ A}$	DO-214AB, SMC	K•A
GDY	SMCJ11	VISH	VS	V _{BR} (I _T = 1.0 mA) = 12.2015.40 B; V _{MM} = 11.0 B; I _{PP} = 74.6 A	DO-214AB, SMC	K•A
GDZ	1SMC11AT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 12.213.5 \text{ B}; V_{WM} = 18.2 \text{ B}; I_{pp} = 82.4 \text{ A}$	DO-214AB, SMC	K∙A
GDZ	SMCJ11A	VISH	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 12.2014.40 \text{ B}; V_{VMM} = 11.0 \text{ B}; I_{pp} = 82.4 \text{ A}$	DO-214AB, SMC	K∙A
GED	SMCJ12	VISH	vs	V _{BR} (I _T = 1.0 mA) = 13.3016.90 B; V _{WM} = 12.0 B; I _{PP} = 68.2 A	DO-214AB, SMC	K∙A
GEE	1SMC12AT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 13.314.7 \text{ B}; V_{WM} = 19.9 \text{ B}; I_{PP} = 75.3 \text{ A}$	DO-214AB, SMC	K•A
GEE	SMCJ12A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 13.3015.30 B; V _{WM} = 12.0 B; I _{PP} = 75.3 A	DO-214AB, SMC	K∙A
GEF	SMCJ13	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 14.4018.20 \text{ B}; V_{MM} = 13.0 \text{ B}; I_{PP} = 63.0 \text{ A}$	DO-214AB, SMC	K•A
GEG	1SMC13AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 14.415.9B; V _{WM} = 21.5B, I _{PP} = 69.7 A	DO-214AB, SMC	K•A
GEG	SMCJ13A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 14.4016.50 B; V _{MM} = 13.0 B; I _{PP} = 69.7 A	DO-214AB, SMC	K∙A
GEH	SMCJ14	VISH	vs	V _{BR} (I _T = 1.0 мA) = 15.6019.80 B; V _{WM} = 14.0 B; I _{PP} = 58.1 A	DO-214AB, SMC	K∙A
GEK	1SMC14AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 15.617.2B; V _{WM} = 23.2B; I _{pp} = 64.7 A	DO-214AB, SMC	K∙A
GEK	SMCJ14A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 15.6017.90 B; V _{WM} = 14.0 B; I _{pp} = 64.7 A	DO-214AB, SMC	K•A





Код	Типономинал	Б	Ф	Особенности	Kopnyc	Ц: 1•2
GEL	SMCJ15	VISH	VS	V _{BR} (I _T = 1.0 mA) = 16.7021.10 B; V _{MM} = 15.0B; I _{PP} = 55.8 A	DO-214AB, SMC	K•A
GEM	1SMC15AT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 16.718.5B; V _{WM} = 24.4B; I _{PP} = 61.5A	DO-214AB, SMC	K•A
GEM	SMCJ15A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 16.7019.20 B; V _{WM} = 15.0 B; I _{PP} = 61.5 A	DO-214AB, SMC	K•A
GEN	SMCJ16	VISH	VS.	V _{BR} (I _T = 1.0 mA) = 17.8022.60 B; V _{WM} = 16.0 B; I _{PP} = 52.1 A	DO-214AB, SMC	K•A
GEP	1SMC16AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 17.819.7B; V _{WM} = 26 B; I _{PP} = 57.7 A	DO-214AB, SMC	K•A
GEP	SMCJ16A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 17.8020.50 B; V _{WM} = 16.0 B; I _{PP} = 57.7 A	DO-214AB, SMC	K•A
GEQ	SMCJ17	VISH	VS	V _{BR} (I _T = 1.0 mA) = 18.9023.90 B; V _{WM} = 17.0B; I _{PP} = 49.2 A	DO-214AB, SMC	K•A
GER	1SMC17AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 18.920.9 \text{B; } V_{WM} = 27.6 \text{B; } I_{PP} = 53.3 \text{A}$	DO-214AB, SMC	K•A
GER	SMCJ17A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 18.9021.70 B; V _{WM} = 17.0 B; I _{PP} = 53.3 A	DO-214AB, SMC	K•A
GES	SMCJ18	VISH	vs	V _{BB} (I _T = 1.0 mA) = 20.0025.30 B; V _{MM} = 18.0 B; I _{pp} = 46.6 A	DO-214AB, SMC	K•A
GET	1SMC18AT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 2022.1B; V _{WM} = 29.2B; I _{PP} = 51.4A	DO-214AB, SMC	K∙A
GET	SMCJ18A	VISH	VS	V _{BB} (I _T = 1.0 mA) = 20.0023.30 B; V _{MM} = 18.0 B; I _{PP} = 51.4 A	DO-214AB, SMC	K•A
GEU	SMCJ20	VISH	VS	V _{BB} (I _T = 1.0 mA) = 22.2028.10 B; V _{MM} = 20.0 B; I _{PP} = 41.9 A	DO-214AB, SMC	K•A
GEV	1SMC20AT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 22.224.5B; V _{WM} = 32.4B; I _{PP} = 46.3A	DO-214AB, SMC	K•A
GEV	SMCJ20A	VISH	vs.	V _{BR} (I _T = 1.0 mA) = 22.2025.50 B; V _{WM} = 20.0 B; I _{PP} = 46.3 A	DO-214AB, SMC	K•A
GEW	SMCJ22	VISH	VS	V _{BR} (I _T = 1.0 mA) = 24.4030.90 B; V _{MM} = 22.0B; I _{PP} = 38.1 A	DO-214AB, SMC	K•A
GEX	1SMC22AT3	ON	VS	V _{BB} (I _T = 1.0 mA) = 24.426.9B; V _{WM} = 35.5B; I _{PP} = 42.2A	DO-214AB, SMC	K•A
GEX	SMCJ22A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 24.4028.00 B; V _{WM} = 22.0B; I _{PP} = 42.2 A	DO-214AB, SMC	K•A
GEY	SMCJ24	VISH	VS	V _{BB} (I _T = 1.0 mA) = 26.7033.80 B; V _{MM} = 24.0B; I _{PP} = 34.9 A	DO-214AB, SMC	K•A
GEZ	1SMC24AT3	ON	VS	V _{BR} (I _T =1.0 MA)=26.729.5B; V _{WM} =38.9B; I _{PP} =38.6A	DO-214AB, SMC	K•A
GEZ	SMCJ24A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 26.7030.70 B; V _{WM} = 24.0 B; I _{PP} = 38.6 A	DO-214AB, SMC	K•A
GFD	SMCJ26	VISH	vs	V _{BR} (I _T = 1.0 MA) = 28.9036.80 B; V _{WM} = 26.0B; I _{PP} = 32.2 A	DO-214AB, SMC	K•A
GFE	1SMC26AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 28.931.9B; V _{WM} = 42.1B; I _{PP} = 35.6A	DO-214AB, SMC	K•A
GFE	SMCJ26A	VISH	VS	V _{BB} (I _T = 1.0 mA) = 28.9033.20 B; V _{MM} = 26.0 B; I _{PP} = 35.6 A	DO-214AB, SMC	K•A
GFF	SMCJ28	VISH	vs	V _{BB} (I _T = 1.0 mA) = 31.1039.40 B; V _{MM} = 28.0 B; I _{PP} = 30.0 A	DO-214AB_SMC	K•A
GFG	1SMC28AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 31.134.4B; V _{WM} = 45.4B; I _{PP} = 33A	DO-214AB, SMC	K•A
GFG	SMCJ28A	VISH	VS	V _{BB} (I _T = 1.0 mA) = 31.1035.80 B; V _{WM} = 28.0 B; I _{PP} = 33.0 A	DO-214AB, SMC	K•A
GFH	SMCJ30	VISH	VS	V _{BR} (I _T = 1.0 MA) = 33.3042.40 B; V _{WM} = 30.0 B; I _{PP} = 28.0 A	DO-214AB, SMC	K•A
GFK	1SMC30AT3	ON	vs	$V_{BB}(I_T = 1.0 \text{ mA}) = 33.336.8B; V_{WM} = 48.4B; I_{PP} = 31A$	DO-214AB, SMC	K•A
GFK	SMCJ30A	VISH	vs	V _{BR} (I _T = 1.0 MA) = 33.3038.30 B; V _{WM} = 30.0 B; I _{PP} = 31.0 A	DO-214AB, SMC	K•A
GFL	SMCJ33	VISH	vs	V _{BB} (I _T = 1.0 MA) = 36.7046.90 B; V _{MM} = 33.0 B; I _{PP} = 25.2 A	DO-214AB, SMC	K•A
GFM	1SMC33AT3	ON	vs.	V _{BR} (I _T =1.0 MA)=36.740.6B; V _{WM} =53.3B; I _{PP} =28.1A	DO-214AB, SMC	K•A
GFM	SMCJ33A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 36.7042.20 B; V _{MM} = 33.0 B; I _{PP} = 28.1 A	DO-214AB, SMC	K•A
GFN	SMCJ36	VISH	vs	V _{BB} (I _T = 1.0 mA) = 40.0050.70 B; V _{MM} = 36.0 B; I _{PP} = 23.3 A	DO-214AB, SMC	K•A
GFP	1SMC36AT3	ON	VS	V _{BR} (I _T =1.0 MA)=40.044.2B; V _{WM} =58.1B; I _{PP} =25.8A	DO-214AB, SMC	K•A
GFP	SMCJ36A	VISH	VS	V _{BB} (I _T = 1.0 MA) = 40.0046.00 B; V _{MM} = 36.0 B; I _{PP} = 25.8 A	DO-214AB, SMC	K•A
GFQ	SMCJ40	VISH	vs	V _{BR} (I _T = 1.0 MA) = 44.4056.30 B; V _{WM} = 40.0B; I _{PP} = 21.0 A	DO-214AB, SMC	K•A
GFR	1SMC40AT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 44.449.1B; V _{WM} = 64.5B; I _{pp} = 32.2A	DO-214AB SMC	K•A
GFR	SMCJ40A	VISH	vs	V _{BR} (I _T = 1.0 MA) = 44.4051.10 B; V _{WM} = 40.0B; I _{PP} = 23.2 A	DO-214AB, SMC	K•A
GFS	SMCJ43	VISH	vs	$V_{BR}(I_T = 1.0 \text{ MA}) = 47.8060.50 \text{ B}; V_{WM} = 43.0 \text{ B}; I_{PP} = 19.6 \text{ A}$	DO-214AB, SMC	K•A
GFT	1SMC43AT3	ON	vs	V _{BB} (I _T = 1.0 MA) = 47.852.8B; V _{WM} = 69.4B; I _{PP} = 21.6A	DO-214AB, SMC	K•A
GFT	SMCJ43A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 47.8054.90 B; V _{MM} = 43.0 B; I _{PP} = 21.6 A	DO-214AB, SMC	K•A
GFU	SMCJ45	VISH	VS	V _{BB} (I _T = 1.0 MA) = 50.0063.30 B; V _{WM} = 45.0 B; I _{PP} = 18.7 A	DO-214AB SMC	K•A
GFV	1SMC45AT3	ON	VS	V _{BB} (I _T = 1.0 MA) = 50.055.3B; V _{WM} = 72.2B; I _{PP} = 20.6A	DO-214AB, SMC	K•A
GFV	SMCJ45A	VISH	VS	V _{BR} (I _T = 1.0 MA) = 50.0057.50 B; V _{WM} = 45.0B; I _{PP} = 20.6 A	DO-214AB, SMC	K•A
GFW	SMCJ48	VISH	VS	V _{BB} (I _T = 1.0 MA) = 53.3067.50 B; V _{MM} = 48.0 B; I _{PP} = 17.5 A	DO-214AB, SMC	K•A
GFX	1SMC48AT3	ON	VS	V _{BB} (I _T = 1.0 mA) = 53.358.9B; V _{WM} = 77.4 B; I _{PP} = 19.4A	DO-214AB, SMC	K•A
GFX	SMCJ48A	VISH	VS	V _{BB} (I _T = 1.0 mA) = 53.3061.30 B; V _{MM} = 48.0 B; I _{PP} = 19.4 A	DO-214AB SMC	K•A
GFY	SMCJ51	VISH	vs	V _{BR} (I _T = 1.0 mA) = 56.7071.80 B; V _{WM} = 51.0B; I _{PP} = 16.5 A	DO-214AB, SMC	K•A
GFZ	1SMC51AT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 56.762.7B; V _{WM} = 82.4B; I _{PP} = 18.2A	DO-214AB, SMC	K•A
GFZ	SMCJ51A	VISH	vs	V _{BB} (I _T = 1.0 MA) = 56.7065.20 B; V _{WM} = 51.0 B; I _{PP} = 18.2 A	DO-214AB, SMC	K•A
GG	GF1G	VISH	dr	V _B <400 B; I _E <1A; V _E (I _E =1A)<1.1 B	DO-214BA	K•A
GG	GF1G	GS	dr	V _B < 400 B; I _E < 1 A; V _E (I _E = 1 A) < 1.1 B	DO-214BA	K•A
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Код	Типономинал	Б	Φ	Особенности	Корпус	Ц: 1•2
GGD	SMCJ54	VISH	vs	V _{BR} (I _T = 1.0 mA) = 60.0076.00 B; V _{VM} = 54.0 B; I _{PP} = 15.6 A	DO-214AB, SMC	K•A
GGE	1SMC54AT3	ON	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 60.066.3 \text{ B}; V_{WM} = 87.1 \text{ B}; I_{pp} = 17.2 \text{ A}$	DO-214AB, SMC	K•A
GGE	SMCJ54A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 60.0069.00 B; V _{WM} = 54.0 B; I _{PP} = 17.2 A	DO-214AB, SMC	K•A
GGF	SMCJ58	VISH	VS	V _{BR} (I _T = 1.0 mA) = 64.4081.60 B; V _{MM} = 58.0 B; I _{PP} = 14.6 A	DO-214AB, SMC	K•A
GGG	1SMC58AT3	ON	νS	V _{BR} (I _T = 1.0 mA) = 64.471.2 B; V _{WM} = 93.6 B; I _{PP} = 16.0 A	DO-214AB, SMC	K∙A
GGG	SMCJ58A	VISH	٧S	V _{BR} (I _T = 1.0 mA) = 64.4074.60 B; V _{WM} = 58.0 B; I _{PP} = 16.0 A	DO-214AB, SMC	K•A
GGH	SMCJ60	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 66.7084.50 \text{ B}; V_{VMM} = 60.0 \text{ B}; I_{PP} = 14.0 \text{ A}$	DO-214AB, SMC	K•A
GGK	1SMC60AT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 66.773.7 \text{ B}; V_{WM} = 96.8 \text{ B}; I_{pp} = 15.5 \text{ A}$	DO-214AB, SMC	K•A
GGK	SMCJ60A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 66.7076.70 B; V _{VM} = 60.0 B; I _{PP} = 15.5 A	DO-214AB, SMC	K•A
GGL	SMCJ64	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 71.1090.10 \text{ B}; V_{WM} = 64.0 \text{ B}; I_{pp} = 13.2 \text{ A}$	DO-214AB, SMC	K•A
GGM	1SMC64AT3	ON	٧S	V _{BR} (I _T = 1.0 mA) = 71.178.6B; V _{WM} = 103B; I _{PP} = 14.6 A	DO-214AB, SMC	K•A
GGM	SMCJ64A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 71.1081.80 B; V _{MM} = 64.0 B; I _{pp} = 14.6 A	DO-214AB, SMC	K•A
GGN	SMCJ70	VISH	vs	V _{BR} (I _T = 1.0 mA) = 77.8098.60 B; V _{WM} = 70.0 B; I _{PP} = 12.0 A	DO-214AB, SMC	K•A
GGP	1SMC70AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 77.886 B; V _{MM} = 113 B; I _{PP} = 13.3 A	DO-214AB, SMC	K∙A
GGP	SMCJ70A	VISH	vs	V _{BB} (I _T = 1.0 mA) = 77.8089.50 B; V _{MM} = 70.0 B; I _{PP} = 13.3 A	DO-214AB, SMC	K•A
GGQ	SMCJ75	VISH	vs	V _{BR} (I _T = 1.0 mA) = 83.30106.00 B; V _{MM} = 75.0 B; I _{PP} = 11.2 A	DO-214AB, SMC	K•A
GGR	1SMC75AT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 83.392.1 B; V _{WM} = 121 B; I _{PP} = 12.4 A	DO-214AB, SMC	K•A
GGR	SMCJ75A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 83.3095.80 B; V _{WM} = 75.0 B; I _{PP} = 12.4 A	DO-214AB, SMC	K•A
GGS	SMCJ78	VISH	vs	V _{BB} (I _T = 1.0 mA) = 86.70110.00 B; V _{MM} = 78.0 B; I _{PP} = 10.8 A	DO-214AB, SMC	K•A
GGT	1SMC78AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 86.795.8 B; V _{WM} = 126 B; I _{PP} = 11.4 A	DO-214AB, SMC	K•A
GGT	SMCJ78A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 86.7099.70 B; V _{MM} = 78.0 B; I _{PP} = 11.4 A	DO-214AB, SMC	K•A
GGU	SMCJ85	VISH	vs	V _{BR} (I _T = 1.0 mA) = 94.40119.20 B; V _{WM} = 85.0 B; I _{PP} = 9.9 A	DO-214AB, SMC	K•A
GGV	SMCJ85A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 94.40108.20 B; V _{MM} = 85.0 B; I _{PP} = 10.4 A	DO-214AB, SMC	K•A
GGW	SMCJ90	VISH	vs	V _{RR} (I _T = 1.0 mA) = 100.00126.50 B; V _{MM} = 90.0 B; I _{PP} = 9.4 A	DO-214AB, SMC	K•A
GGX	SMCJ90A	VISH	vs	V _{BB} (I _T = 1.0 mA) = 100.00115.50 B; V _{MM} = 90.0 B; I _{PP} = 10.3 A	DO-214AB, SMC	K•A
GGY	SMCJ100	VISH	VS	V _{BB} (I _T = 1.0 mA) = 111.00141.00 B; V _{MM} = 100.0 B; I _{PP} = 8.4A	DO-214AB, SMC	K•A
GGZ	SMCJ100A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 111.00128.00 B; V _{MM} = 100.0 B; I _{PP} = 9.3 A	DO-214AB, SMC	K•A
GHD	SMCJ110	VISH	vs	V _{BB} (I _T = 1.0 mA) = 122.00154.50 B; V _{MM} = 110.0 B; I _{PP} = 7.7A	DO-214AB, SMC	K•A
GHE	SMCJ110A	VISH	vs	V _{BB} (I _T = 1.0 mA) = 122.00140.50 B; V _{MM} = 110.0 B; I _{PP} = 8.4 A	DO-214AB, SMC	K•A
GHF	SMCJ120	VISH	vs	V _{BR} (I _T = 1.0 mA) = 133.00169.00 B; V _{MM} = 120.0 B; I _{PP} = 7.0 A	DO-214AB, SMC	K•A
GHG	SMCJ120A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 133.00153.00 B; V _{MM} = 120.0 B; I _{PP} = 7.9 A	DO-214AB, SMC	K•A
GHH	SMCJ130	VISH	vs	V _{BR} (I _T = 1.0 mA) = 144.00182.50 B; V _{MM} = 130.0 B; I _{PP} = 6.5 A	DO-214AB, SMC	K•A
GHK	SMCJ130A	VISH	vs	V _{BB} (I _T = 1.0 mA) = 144.00165.50 B; V _{MM} = 130.0 B; I _{PP} = 7.2 A	DO-214AB, SMC	K•A
GHL	SMCJ150	VISH	vs	V _{BB} (I _T = 1.0 mA) = 167.00211.50 B; V _{MM} = 150.0 B; I _{PP} = 5.6A	DO-214AB, SMC	K•A
GHM	SMCJ150A	VISH	vs	V _{BB} (I _T = 1.0 mA) = 167.00192.50 B; V _{MM} = 150.0 B; I _{DD} = 6.2 A	DO-214AB, SMC	K•A
GHN	SMCJ160	VISH	vs	V _{BR} (I _T = 1.0 mA) = 178.00226.00 B; V _{WM} = 160.0 B; I _{PP} = 5.2 A	DO-214AB, SMC	K•A
GHP	SMCJ160A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 178.00205.00 B; V _{WM} = 160.0 B; I _{PP} = 5.8A	DO-214AB, SMC	K•A
GHQ	SMCJ170	VISH	VS	V _{BB} (I _T = 1.0 mA) = 189.00239.50 B; V _{MM} = 170.0 B; I _{PP} = 4.9 A	DO-214AB, SMC	K•A
GHR	SMCJ170A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 189.00217.50 B; V _{WM} = 170.0 B; I _{PP} = 5.5A	DO-214AB, SMC	K•A
GJ	GF1J	VISH	dr	V _R <600 B; I _F <1A; V _F (I _F =1A)<1.1B	DO-214BA	K•A
GJ	GF1J	GS	dr	V _B <600 B; I _E <1 A; V _E (I _E =1 A)<1.1 B	DO-214BA	K•A
GK	GF1K	VISH	dr	V _B < 800 B; I _F < 1.A; V _F (I _F = 1.A) < 1.2B	DO-214BA	K•A
GK	GF1K	GS	dr	V _R < 800 B; I _E < 1 A; V _E (I _E = 1 A) < 1.2 B	DO-214BA	K•A
GM	GF1M	VISH	dr	V _R <1000 B; I _E <1A; V _E (I _E =1A)<1.2B	DO-214BA	K•A
GM	GF1M	GS	dr	V _B <1000 B; I _E <1A; V _E (I _E =1A)<1.2B	DO-214BA	K•A
GUA	SMCJ60A	STM	vs	V _{BR} (I _T =1.0 mA)=66.7076.70 B; V _{MM} =60.0 B; I _{PP} =15.5 A	DO-214BA SMC	K•A
GUB	SMCJ70A	STM	vs	V _{BR} (I _T = 1.0 MA) = 77.8089.50 B; V _{VM} = 70.0 B; I _{PP} = 13.3 A	DO-214AB, SMC	K•A
GUE	SMCJ70A SMCJ85A	STM	vs vs	$V_{BR}(I_T = 1.0 \text{ MA}) = 77.8089.50 \text{ B}; V_{MM} = 70.0 \text{ B}; I_{PP} = 13.3 \text{ A}$ $V_{BR}(I_T = 1.0 \text{ MA}) = 94.40108.20 \text{ B}; V_{MM} = 85.0 \text{ B}; I_{PP} = 10.4 \text{ A}$	DO-214AB, SMC	K•A
GUG	SMCJ100A	STM	vs vs	V _{BR} (I _T = 1.0 MA) = 94.40 100.20 B, V _{MM} = 05.0 B, I _{pp} = 10.4 A V _{BR} (I _T = 1.0 MA) = 111.00141.00 B; V _{MM} = 100.0 B; I _{pp} = 8.4 A	DO-214AB, SMC	K•A
GUI	SMCJ100A SMCJ130A	STM		COLUMN TO THE PROPERTY OF THE	DO-214AB, SMC	K•A
GUL	SMCJ150A SMCJ154A	STM	VS uc	V _{BR} (I _T = 1.0 mA) = 144.00182.50 B; V _{MM} = 130.0 B; I _{PP} = 6.5 A V _C (I _C = 1.0 mA) = 171 B; V _C = 154.0 B; I _C = 6.1 A	DO-214AB, SMC	K•A
GUM		200,000	vs	V _{BR} (I _T = 1.0 mA) = 171 B; V _{WM} = 154.0 B; I _{PP} = 6.1 A		
	SMCJ170A	STM	VS	V _{BR} (I _T = 1.0 mA) = 189.00217.50 B; V _{WM} = 170.0 B; I _{PP} = 5.5A	DO-214AB, SMC	K•A
GUN	SMCJ188A	STM	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 209 \text{ B}; V_{WM} = 188.0 \text{ B}; I_{pp} = 4.6 \text{ A}$	DO-214AB, SMC	K•A





Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2
HD	SMAJ5.0	VISH	VS	V _{BR} (I _T = 10.0 mA) = 6.407.30B; V _{WM} = 9.6B; I _{PP} = 41.6A	DO-214AC, SMA	K•A
HE	SMAJ5.0A	VISH	VS	V _{BR} (I _T = 10.0 mA) = 6.47.0 B; V _{WM} = 9.2 B; I _{PP} = 43.5 A	DO-214AC, SMA	K•A
HF	SMAJ6.0	VISH	VS	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.678.15 \text{ B}; V_{WM} = 11.4 \text{ B}; I_{pp} = 35.1 \text{ A}$	DO-214AC, SMA	K•A
HG	SMAJ6.0A	VISH	VS	V _{BR} (I _T = 10.0 mA) = 6.677.37B; V _{WM} = 10.3 B; I _{PP} = 38.8A	DO-214AC, SMA	K•A
HH	SMAJ6.5	VISH	VS	V _{BR} (I _T = 10.0 mA) = 7.228.82B; V _{WM} = 12.3 B; I _{pp} = 32.5 A	DO-214AC, SMA	K•A
HK	SMAJ6.5A	VISH	VS	V _{BR} (I _T = 10.0 mA) = 7.227.98 B; V _{WM} = 11.2 B; I _{PP} = 35.7A	DO-214AC, SMA	K•A
HL	SMAJ7.0	VISH	VS	V _{BR} (I _T = 10.0 mA) = 7.789.51 B; V _{WM} = 13.3 B; I _{PP} = 30.1 A	DO-214AC, SMA	K•A
НМ	SMAJ7.0A	VISH	VS	V _{BB} (I _T = 10.0 mA) = 7.788.60 B; V _{WM} = 12.0 B; I _{PP} = 33.3 A	DO-214AC, SMA	K•A
HN	SMAJ7.5	VISH	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 8.3310.3 \text{ B}; V_{WM} = 14.3 \text{ B}; I_{PP} = 28.0 \text{ A}$	DO-214AC, SMA	K•A
HP	SMAJ7.5A	VISH	VS	V _{BB} (I _T = 1.0 mA) = 8.339.21 B; V _{WM} = 12.9 B; I _{PP} = 31.0 A	DO-214AC, SMA	K•A
HQ	SMAJ8.0	VISH	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 8.8910.9B; V_{WM} = 15.0B; I_{PP} = 26.5A$	DO-214AC, SMA	K•A
HR	SMAJ8.0A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ MA}) = 8.899.83 \text{ B; } V_{WM} = 13.6 \text{ B; } I_{PP} = 29.4 \text{ A}$	DO-214AC, SMA	K•A
HS	SMAJ8.5	VISH	VS	V _{BR} (I _T = 1.0 MA) = 9.4411.5B; V _{WM} = 15.9B; I _{PP} = 25.1A	DO-214AC, SMA	K•A
нт	SMAJ8.5A	VISH	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 9.4410.4 \text{ B}; V_{WM} = 14.4 \text{ B}; I_{PP} = 27.7 \text{ A}$	DO-214AC, SMA	K•A
HU	SMAJ9.0	VISH	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 10.012.2B; V_{WM} = 16.9 \text{ B}; I_{PP} = 23.6 \text{ A}$	DO-214AC, SMA	K•A
HV	SMAJ9.0A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 10.011.1 B; V _{WM} = 15.4 B; I _{PP} = 26.0 A	DO-214AC, SMA	K•A
HW	SMAJ10	VISH	VS	V _{BR} (I _T = 1.0 mA) = 11.113.6B; V _{WM} = 18.8B; I _{PP} = 21.2A	DO-214AC SMA	K•A
НХ	SMAJ10A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 11.112.3B; V _{WM} = 17.0B; I _{PP} = 23.5A	DO-214AC SMA	K•A
HY	SMAJ11	VISH	VS	V _{BR} (I _T = 1.0 mA) = 12.214.9B; V _{WM} = 20.1 B; I _{FP} = 20.0 A	DO-214AC, SMA	K•A
HZ	SMAJ11A	VISH	VS	V _{BB} (I _T = 1.0 mA) = 12.213.5B; V _{WM} = 18.2B; I _{PP} = 22.0A	DO-214AC, SMA	K•A
ID	SMAJ12	VISH	VS	V _{BR} (I _T = 1.0 mA) = 13.316.3B; V _{WM} = 22.0B; I _{PP} = 18.1A	DO-214AC, SMA	K•A
IE .	SMAJ12A	VISH	vs	V _{BB} (I _T = 1.0 mA) = 13.314.7B; V _{WM} = 19.9B; I _{PP} = 20.1A	DO-214AC, SMA	K•A
IF.	SMAJ13	VISH	VS	V _{BB} (I _T = 1.0 mA) = 14.417.6B; V _{WM} = 23.8B; I _{PP} = 16.8A	DO-214AC, SMA	K•A
IG	SMAJ13A	VISH	VS	V _{BR} (I _T = 1.0 MA) = 14.415.9B; V _{WM} = 21.5B; I _{PP} = 18.6A	DO-214AC SMA	K•A
IH .	SMAJ14	VISH	VS	V _{BB} (I _T =1.0 MA)=15.619.1B; V _{WM} =25.8B; I _{PP} =15.5A	DO-214AC SMA	K•A
IK	SMAJ14A	VISH	VS	V _{BB} (I _T = 1.0 MA) = 15.617.2B; V _{WM} = 23.2B; I _{PP} = 17.2A	DO-214AC SMA	K•A
IL .	SMAJ15	VISH	VS	V _{BB} (I _T = 1.0 MA) = 16.720.4 B; V _{WM} = 26.9 B; I _{PP} = 14.8 A	DO-214AC, SMA	K•A
IM	SMAJ15A	VISH	VS	V _{BB} (I _T = 1.0 MA) = 16.718.5B; V _{WM} = 24.4B; I _{PP} = 16.4A	DO-214AC, SMA	K•A
IN	SMAJ16	VISH	VS.	V _{BB} (I _T = 1.0 MA) = 17.821.8B; V _{WM} = 28.8B; I _{PP} = 13.8A	DO-214AC SMA	K•A
IP	SMAJ16A	VISH	vs vs	V _{BB} (I _T = 1.0 MA) = 17.819.7B; V _{WM} = 26.0B; I _{PP} = 15.3A	DO-214AC SMA	K•A
IQ	SMAJ17	VISH	VS	V _{BB} (I _T = 1.0 MA) = 18.9., 23.1 B; V _{WM} = 30.5 B; I _{PP} = 13.1 A	DO-214AC SMA	K•A
IR	SMAJ17A	VISH	VS VS	V _{BB} (I _T = 1.0 MA) = 18.920.9B; V _{WM} = 27.6B; I _{PP} = 14.5A	DO-214AC, SMA	K•A
IS	SMAJ18	VISH	VS VS	V _{BB} (I _T = 1.0 MA) = 20.024.4 B; V _{WM} = 32.2 B; I _{PP} = 12.4 A	DO-214AC, SMA	K•A
ΙΤ	SMAJ18A	VISH	VS VS	V _{BB} (I _T = 1.0 MA) = 20.022.1 B; V _{WM} = 32.2 B; I _{PP} = 13.7 A	DO-214AC, SMA	K•A
IU	SMAJ20	VISH	VS VS	V _{BB} (I _T = 1.0 MA) = 22.227.1 B; V _{WM} = 25.8 B; I _{PP} = 11.1 A	DO-214AC SMA	K•A
IV	SMAJ20A	VISH	VS VS		DO-214AC SMA	K•A
IW	SMAJ20A SMAJ22	VISH		V _{BR} (I _T = 1.0 mA) = 22.224.5B; V _{WM} = 32.4B; I _{PP} = 12.3A	- C	K•A
IX		VISH	VS	V _{BR} (I _T = 1.0 MA) = 24.429.8 B; V _{WM} = 39.4 B; I _{PP} = 10.1 A	DO-214AC, SMA	K•A
IY	SMAJ22A SMAJ24	VISH	VS	V _{BR} (I _T = 1.0 mA) = 24.426.9B; V _{WM} = 35.5B; I _{PP} = 11.2A	DO-214AC, SMA	K•A
			VS	V _{BR} (I _T = 1.0 MA) = 26.732.6B; V _{WM} = 43.0B; I _{PP} = 9.3A	DO-214AC, SMA	175 65
IZ	SMAJ24A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 26.729.5B; V _{WM} = 38.9B; I _{PP} = 10.3A	DO-214AC, SMA	K•A
JD	SMAJ26	VISH	VS	V _{BR} (I _T = 1.0 mA) = 28.931.9B; V _{WM} = 46.6B; I _{PP} = 8.6A	DO-214AC SMA	K•A
JE	SMAJ26A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 28.925.3 \text{ B; } V_{WM} = 42.1 \text{ B; } I_{PP} = 9.5 \text{ A}$	DO-214AC SMA	K•A
JF	SMAJ28	VISH	VS	V _{BR} (I _T = 1.0 mA) = 31.138.0B; V _{WM} = 50.0B; I _{pp} = 8.0A	DO-214AC, SMA	K•A
JG	SMAJ28A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 31.134.4 \text{ B}; V_{WM} = 45.4 \text{ B}; I_{pp} = 8.8 \text{ A}$	DO-214AC, SMA	K•A
JH	SMAJ30	VISH	VS	V _{BR} (I _T = 1.0 mA) = 33.340.7B; V _{WM} = 53.5 B; I _{PP} = 7.5 A	DO-214AC, SMA	K•A
JK	SMAJ30A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 33.336.8B; V_{WM} = 48.4 B; I_{PP} = 8.3 A.$	DO-214AC, SMA	K•A
JL	SMAJ33	VISH	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 36.744.9B; V_{WM} = 59.0B; I_{PP} = 6.8A$	DO-214AC SMA	K•A
JM	SMAJ33A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 36.740.6B; V_{WM} = 53.3 \text{ B}; I_{PP} = 7.5 \text{ A}$	DO-214AC, SMA	K•A
JN	SMAJ36	VISH	VS	V _{BR} (I _T = 1.0 mA) = 40.048.9B; V _{WM} = 64.3B; I _{PP} = 6.2A	DO-214AC, SMA	K•A
JP	SMAJ36A	VISH	VS	V _{BR} (I _T = 1.0 MA) = 40.044.2B; V _{WM} = 58.1 B; I _{PP} = 6.9A	DO-214AC, SMA	K•A
JQ	SMAJ40	VISH	VS	V _{BR} (I _T =1.0 MA)=44.454.3B; V _{WM} =71.4B; I _{PP} =5.6A	DO-214AC, SMA	K•A
JR	SMAJ40A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ MA}) = 44.449.1 \text{ B}; V_{WM} = 64.5 \text{ B}; I_{PP} = 6.2 \text{ A}$	DO-214AC, SMA	K•A
JS	SMAJ43	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 47.858.4B; V_{WM} = 76.7B; I_{PP} = 5.2A$	DO-214AC, SMA	K•A



Код	Типономинал	Б	Φ	Особенности	Корпус	Ц: 1•2
JT	SMAJ43A	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 47.852.8 \text{ B}; V_{WM} = 69.4 \text{ B}; I_{pp} = 5.7 \text{ A}$	DO-214AC, SMA	K•A
JU	SMAJ45	VISH	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 50.061.1 \text{ B}; V_{WM} = 80.3 \text{ B}; I_{pp} = 5.0 \text{ A}$	DO-214AC, SMA	K•A
JV	SMAJ45A	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 50.055.3 \text{ B}; V_{WM} = 72.7 \text{ B}; I_{pp} = 5.5 \text{ A}$	DO-214AC, SMA	K•A
JW	SMAJ48	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 53.365.1 \text{ B}; V_{WM} = 85.5 \text{ B}; I_{PP} = 4.7 \text{ A}$	DO-214AC, SMA	K•A
JX	SMAJ48A	VISH	νS	$V_{BR}(I_T = 1.0 \text{ mA}) = 53.358.9 \text{B}; V_{WM} = 77.4 \text{B}; I_{pp} = 5.2 \text{A}$	DO-214AC, SMA	K∙A
JY	SMAJ51	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 56.769.3 \text{ B; } V_{WM} = 91.1 \text{ B; } I_{PP} = 4.4 \text{ A}$	DO-214AC, SMA	K•A
JZ	SMAJ51A	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 56.762.7 \text{ B}; V_{WM} = 82.4 \text{ B}; I_{pp} = 4.9 \text{ A}$	DO-214AC, SMA	K•A
KD	SMBJ5.0	VISH	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.407.55 \text{ B}; V_{WM} = 5.0 \text{ B}; I_{pp} = 62.5 \text{ A}$	DO-214AA, SMB	K•A
KDP	TPSMB6.8	GS	vs	V _{BR} (I _T = 10.0 mA) = 6.127.48 B; V _{WM} = 5.50 B; I _{PP} = 55.6 A	DO-214AA, SMB	K•A
KE	1SMB5.0AT3	ON	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.47.0 \text{ B}; V_{WM} = 9.2 \text{ B}; I_{pp} = 65.2 \text{ A}$	DO-214AA, SMB	K•A
KE	SMBJ5.0A	VISH	٧S	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.407.23 \text{ B}; V_{WM} = 5.0 \text{ B}; I_{PP} = 65.2 \text{ A}$	DO-214AA, SMB	K•A
KEP	TPSMB6.8A	GS	vs	V _{BR} (I _T = 10.0 mA) = 6.457.14 B; V _{WM} = 5.80 B; I _{PP} = 57.1 A	DO-214AA, SMB	K•A
KF	SMBJ6.0	VISH	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.678.45 \text{ B}; V_{WM} = 6.0 \text{ B}; I_{PP} = 52.6 \text{ A}$	DO-214AA, SMB	K•A
KFP	TPSMB7.5	GS	vs	V _{BR} (I _T = 10.0 mA) = 6.758.25 B; V _{WM} = 6.05 B; I _{PP} = 51.3 A	DO-214AA, SMB	K•A
KG	1SMB6.0AT3	ON	vs	V _{BB} (I _T = 10.0 mA) = 6.677.37 B; V _{WM} = 10.3 B; I _{PP} = 58.3 A	DO-214AA, SMB	K•A
KG	SMBJ6.0A	VISH	VS	V _{BR} (I _T = 10.0 mA) = 6.677.67 B; V _{WM} = 6.0 B; I _{PP} = 58.3 A	DO-214AA, SMB	K•A
KGP	TPSMB7.5A	GS	vs	V _{BB} (I _T = 10.0 mA) = 7.137.88 B; V _{WM} = 6.40 B; I _{PP} = 53.1 A	DO-214AA, SMB	K•A
KH	SMBJ6.5	VISH	vs	V _{BR} (I _T = 10.0 mA) = 7.229.14 B; V _{WM} = 6.5 B; I _{PP} = 48.7 A	DO-214AA, SMB	K•A
KHP	TPSMB8.2	GS	vs	V _{BR} (I _T = 10.0 mA) = 7.389.02 B; V _{WM} = 6.63 B; I _{PP} = 48.0 A	DO-214AA, SMB	K•A
KK	1SMB6.5AT3	ON	vs	V _{BR} (I _T = 10.0 mA) = 7.227.98 B; V _{WM} = 11.2 B; I _{PP} = 53.6 A	DO-214AA, SMB	K•A
KK	SMBJ6.5A	VISH	vs	V _{BR} (I _T = 10.0 mA) = 7.228.30 B; V _{WM} = 6.5 B; I _{PP} = 53.6 A	DO-214AA, SMB	K•A
KKP	TPSMB8.2A	GS	vs	V _{BB} (I _T = 10.0 mA) = 7.798.61 B; V _{WM} = 7.02 B; I _{PP} = 49.6 A	DO-214AA, SMB	K•A
KL	SMBJ7.0	VISH	vs	V _{BB} (I _T = 10.0 mA) = 7.789.86 B; V _{WM} = 7.0B; I _{PP} = 45.1 A	DO-214AA, SMB	K•A
KLP	TPSMB9.1	GS	vs	V _{RR} (I _T = 1.0 mA) = 8.1910.0 B; V _{WM} = 7.37 B; I _{DD} = 43.5 A	DO-214AA, SMB	K•A
KM	1SMB7.0AT3	ON	vs	V _{BB} (I _T = 10.0 mA) = 7.788.6B; V _{WM} = 12.0B; I _{DD} = 50.0 A	DO-214AA, SMB	K•A
KM	SMBJ7.0A	VISH	VS	V _{BB} (I _T = 10.0 mA) = 7.788.95 B; V _{WM} = 7.0B; I _{DP} = 50.0 A	DO-214AA, SMB	K•A
KMP	TPSMB9.1A	GS	VS	V _{BB} (I _T = 1.0 mA) = 8.659.55B; V _{WM} = 7.78B; I _{pp} = 44.8A	DO-214AA, SMB	K•A
KN	SMBJ7.5	VISH	vs	V _{BR} (I _T = 1.0 mA) = 8.3310.80 B; V _{WM} = 7.5B; I _{PP} = 42.0A	DO-214AA, SMB	K•A
KNP	TPSMB10	GS	vs	V _{BB} (I _T = 1.0 mA) = 9.0011.0B; V _{WM} = 8.10B; I _{pp} = 40.0A	DO-214AA, SMB	K•A
KP	1SMB7.5AT3	ON	vs	V _{BB} (I _T = 1.0 MA) = 8.339.21B; V _{WM} = 12.9B; I _{PP} = 46.5A	DO-214AA, SMB	K•A
KP	SMBJ7.5A	VISH	vs vs	V _{BR} (I _T = 1.0 mA) = 8.339.58 B; V _{WM} = 7.5B; I _{PP} = 46.5A	DO-214AA, SMB	K•A
KPP	TPSMB10A	GS	VS	V _{BR} (I _T = 1.0 MA) = 0.559.56 B, V _{WM} = 7.5B, I _{PP} = 45.5A V _{BR} (I _T = 1.0 MA) = 9.5010.5B; V _{WM} = 8.55B; I _{PP} = 41.4A	DO-214AA, SMB	K•A
KQ	SMBJ8.0	VISH	vs	V _{BR} (I _T = 1.0 mA) = 8.8911.30 B; V _{WM} = 8.0B; I _{PP} = 40.0 A	DO-214AA, SMB	K•A
KQP	TPSMB11	GS	vs vs	V _{BR} (I _T = 1.0 MA) = 9.9012.1B; V _{MM} = 8.92B; I _{pp} = 37.0A	DO-214AA, SMB	K•A
KR	1SMB8.0AT3	ON	vs vs	V _{BR} (I _T = 1.0 MA) = 8.899.83 B; V _{WM} = 13.6 B; I _{PP} = 44.1 A	DO-214AA, SMB	K•A
KR	SMBJ8.0A	VISH	VS VS	V _{BR} (I _T =1.0 MA)=8.8910.23 B; V _{WM} =8.0B; I _{pp} =44.1 A	DO-214AA, SMB	K•A
KRP	TPSMB11A	GS	vs vs	V _{BB} (I _T =1.0 MA)=0.0510.25 B, V _{MM} =0.05, I _{DP} =44TA V _{BB} (I _T =1.0 MA)=10.511.6B; V _{MM} =9.40B; I _{DP} =38.5A	DO-214AA, SMB	K•A
KS	SMBJ8.5	VISH	_			
KSP	TPSMB12	GS	vs	V _{BR} (I _T =1.0 mA) = 9.4411.92 B; V _{WM} = 8.5 B; I _{PP} = 37.7 A	DO-214AA, SMB	K•A
KT	0.800 0.000 0.000		VS	V _{BR} (I _T = 1.0 mA) = 10.813.2B; V _{WM} = 9.72B; I _{PP} = 34.7A	DO-214AA, SMB	K•A
	1SMB8.5AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 9.4410.4B; V _{WM} = 14.4B; I _{pp} = 41.7A	DO-214AA, SMB	K•A
KT	SMBJ8.5A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 9.4410.82 \text{ B; } V_{MM} = 8.5 \text{ B; } I_{pp} = 41.7 \text{ A}$	DO-214AA, SMB	K•A
KTP	TPSMB12A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 11.412.6 \text{ B}; V_{WM} = 10.2 \text{ B}; I_{PP} = 35.9 \text{ A}$	DO-214AA, SMB	K•A
KU	SMBJ9.0	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 10.0012.80 \text{ B}; V_{WM} = 9.0 \text{ B}; I_{pp} = 35.5 \text{ A}$	DO-214AA, SMB	K•A
KUP	TPSMB13	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 11.714.3 \text{ B}; V_{WM} = 10.5 \text{ B}; I_{pp} = 31.6 \text{ A}$	DO-214AA, SMB	K•A
KV	1SMB9.0AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 10.011.1 \text{ B}; V_{WM} = 15.4 \text{ B}; I_{pp} = 39 \text{ A}$	DO-214AA, SMB	K•A
KV	SMBJ9.0A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 10.0011.50 \text{ B}; V_{MM} = 9.0 \text{ B}; I_{PP} = 39.0 \text{ A}$	DO-214AA, SMB	K•A
KVP	TPSMB13A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 12.413.7 \text{ B}; V_{WM} = 11.1 \text{ B}; I_{PP} = 33.0 \text{ A}$	DO-214AA, SMB	K•A
K₩	SMBJ10	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 11.1014.10 \text{ B}; V_{WM} = 10.0 \text{ B}; I_{PP} = 31.9 \text{ A}$	DO-214AA, SMB	K•A
KWP	TPSMB15	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 13.516.5 \text{ B}; V_{WM} = 12.1 \text{ B}; I_{PP} = 27.3 \text{ A}$	DO-214AA, SMB	K•A
KX	1SMB10AT3	ON	νs	V _{BR} (I _T = 1.0 mA) = 11.112.3 B; V _{WM} = 17B; I _{PP} = 35.3 A	DO-214AA, SMB	K•A
KX	SMBJ10A	VISH	νs	$V_{BR}(I_T = 1.0 \text{ mA}) = 11.1012.80 \text{ B}; V_{WM} = 10.0 \text{ B}; I_{PP} = 35.3 \text{ A}$	DO-214AA, SMB	K∙A
KXC	1SMB10CAT3	ON	νs	$V_{BR}(I_T = 1.0 \text{ mA}) = 11.112.27 \text{ B; } V_{WM} = 17 \text{ B; } I_{PP} = 35.3 \text{ A}$	DO-214AA, SMB	х∙х
KXP	TPSMB15A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 14.315.8 \text{ B}; V_{WM} = 12.8 \text{ B}; I_{pp} = 28.3 \text{ A}$	DO-214AA, SMB	K•A





Код	Типономинал	6	Φ	Особенности	Kopnyc	Ц: 1•2
KY	SMBJ11	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 12.2015.40 \text{ B}; V_{MM} = 11.0 \text{ B}; I_{pp} = 29.9 \text{ A}$	DO-214AA, SMB	K•A
KYP	TPSMB16	GS	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 14.417.6B; V_{WM} = 12.9B; I_{PP} = 25.5A$	DO-214AA, SMB	K•A
KZ	1SMB11AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 12.213.5 \text{ B}; V_{WM} = 18.2 \text{ B}; I_{PP} = 33 \text{ A}$	DO-214AA, SMB	K•A
KZ	SMBJ11A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 12.2014.40 \text{ B}; V_{MM} = 11.0 \text{ B}; I_{PP} = 33.0 \text{ A}$	DO-214AA, SMB	K•A
KZC	1SMB11CAT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 12.213.5 \text{B}; V_{WM} = 18.2 \text{B}; I_{PP} = 33 \text{A}$	DO-214AA, SMB	х∙х
KZP	TPSMB16A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 15.216.8 \text{ B}; V_{WM} = 13.6 \text{ B}; I_{PP} = 26.7 \text{ A}$	DO-214AA, SMB	K•A
Ф	SMBJ12	VISH	VS	$V_{BR}(I_T = 1.0 \text{ MA}) = 13.3016.90 \text{ B}; V_{MM} = 12.0 \text{ B}; I_{PP} = 27.3 \text{ A}$	DO-214AA, SMB	K•A
LDP	TPSMB18	GS	VS	$V_{BR}(I_T = 1.0 \text{ MA}) = 16.219.8 \text{ B}; V_{WM} = 14.5 \text{ B}; I_{PP} = 22.6 \text{ A}$	DO-214AA, SMB	K•A
LE.	1SMB12AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 13.314.7 \text{ B}; V_{WM} = 19.9 \text{ B}; I_{PP} = 30.2 \text{ A}$	DO-214AA, SMB	K•A
LE .	SMBJ12A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 13.3015.30 \text{ B}; V_{MM} = 12.0 \text{ B}; I_{pp} = 30.2 \text{ A}$	DO-214AA, SMB	K•A
LEC	1SMB12CAT3	ON	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 13.314.7 \text{B}; V_{WM} = 19.9 \text{B}; I_{PP} = 30.2 \text{A}$	DO-214AA, SMB	х∙х
LEP	TPSMB18A	GS	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 17.118.9 \text{ B}; V_{WM} = 15.3 \text{ B}; I_{PP} = 23.8 \text{ A}$	DO-214AA, SMB	K•A
LF.	SMBJ13	VISH	VS	$V_{BR}(I_T = 1.0 \text{ MA}) = 14.4018.20 \text{ B}; V_{MM} = 13.0 \text{ B}; I_{PP} = 25.2 \text{ A}$	DO-214AA, SMB	K•A
LFP	TPSMB20	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 18.022.0 \text{ B}; V_{WM} = 16.2 \text{ B}; I_{PP} = 20.6 \text{ A}$	DO-214AA, SMB	K•A
LG	1SMB13AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 14.415.9 \text{ B}; V_{WM} = 21.5 \text{ B}; I_{PP} = 27.9 \text{ A}$	DO-214AA, SMB	K•A
LG	SMBJ13A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 14.4016.50 \text{ B}; V_{MM} = 13.0 \text{ B}; I_{PP} = 27.9 \text{ A}$	DO-214AA, SMB	K•A
LGC	1SMB13CAT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 14.415.9 \text{B}; V_{WM} = 21.5 \text{B}; I_{PP} = 27.9 \text{A}$	DO-214AA, SMB	χ●х
Ш	SMBJ14	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 15.6019.80 \text{ B}; V_{MM} = 14.0 \text{ B}; I_{PP} = 23.3 \text{ A}$	DO-214AA, SMB	K•A
LHP	TPSMB22	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 19.824.2 \text{B}; V_{WM} = 17.8 \text{B}; I_{PP} = 18.8 \text{A}$	DO-214AA, SMB	K•A
LK	1SMB14AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 15.617.2 \text{B}; V_{WM} = 23.2 \text{B}; I_{PP} = 25.8 \text{A}$	DO-214AA, SMB	K•A
LK	SMBJ14A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 15.6017.90 B; V _{MM} = 14.0B; I _{PP} = 25.8 A	DO-214AA, SMB	K•A
LKC	1SMB14CAT3	ON	VS	V _{BB} (I _T =1.0 MA)=15.617.2B; V _{WM} =23.2B; I _{PP} =25.8A	DO-214AA, SMB	х∙х
LKP	TPSMB22A	GS	VS	V _{BB} (I _T = 1.0 mA) = 20.923.1 B; V _{WM} = 18.8 B; I _{PP} = 19.6 A	DO-214AA, SMB	K•A
Щ	SMBJ15	VISH	VS	V _{BR} (I _T = 1.0 mA) = 16.7021.10 B; V _{MM} = 15.0B; I _{pp} = 22.3 A	DO-214AA, SMB	K•A
ШΡ	TPSMB24	GS	VS	V _{BB} (I _T =1.0 mA)=21.626.4B; V _{WM} =19.4B; I _{PP} =17.3A	DO-214AA, SMB	K•A
LM	1SMB15AT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 16.718.5B; V _{WM} = 24.4B; I _{PP} = 24A	DO-214AA, SMB	K•A
LM	SMBJ15A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 16.7019.20 \text{ B}; V_{MM} = 15.0 \text{ B}; I_{PP} = 24.0 \text{ A}$	DO-214AA, SMB	K•A
LMC	1SMB15CAT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 16.718.5 \text{ B}; V_{WM} = 24.4 \text{ B}; I_{PP} = 24 \text{ A}$	DO-214AA, SMB	х∙х
LMP	TPSMB24A	GS	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 22.825.2 \text{B}; V_{WM} = 20.5 \text{B}; I_{PP} = 18.1 \text{A}$	DO-214AA, SMB	K•A
LN	SMBJ16	VISH	VS	V _{BR} (I _T = 1.0 MA) = 17.8022.60 B; V _{MM} = 16.0 B; I _{PP} = 20.8 A	DO-214AA, SMB	K•A
LNP	TPSMB27	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 24.329.7 \text{ B}; V_{WM} = 21.8 \text{ B}; I_{PP} = 15.3 \text{ A}$	DO-214AA, SMB	K•A
LP	1SMB16AT3	ON	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 17.819.7 \text{ B}; V_{WM} = 26 \text{ B}; I_{PP} = 23.1 \text{ A}$	DO-214AA, SMB	K•A
LP	SMBJ16A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 17.8020.50 B; V _{MM} = 16.0 B; I _{PP} = 23.1 A	DO-214AA, SMB	K•A
LPC	1SMB16CAT3	ON	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 17.819.7 \text{B}; V_{WM} = 26 \text{ B}; I_{PP} = 23.1 \text{ A}$	DO-214AA, SMB	х∙х
LPP	TPSMB27A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 25.728.4 \text{ B}; V_{WM} = 23.1 \text{ B}; I_{PP} = 16.0 \text{ A}$	DO-214AA, SMB	K•A
LQ	SMBJ17	VISH	VS	V _{BB} (I _T =1.0 mA)=18.9023.90 B; V _{MM} =17.0B; I _{PP} =19.7 A	DO-214AA, SMB	K•A
LQP	TPSMB30	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 27.033.0 \text{ B}; V_{WM} = 24.3 \text{ B}; I_{pp} = 13.8 \text{ A}$	DO-214AA, SMB	K•A
LR	1SMB17AT3	ON	VS	V _{BB} (I _T =1.0 mA)=18.920.9B; V _{WM} =27.6B; I _{PP} =21.7A	DO-214AA, SMB	K•A
LR	SMBJ17A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 18.9021.70 B; V _{MM} = 17.0B; I _{pp} = 21.7 A	DO-214AA, SMB	K•A
LRC	1SMB17CAT3	ON	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 18.920.9 \text{ B}; V_{WM} = 27.6 \text{ B}; I_{PP} = 21.7 \text{ A}$	DO-214AA, SMB	х∙х
LRP	TPSMB30A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 28.531.5 \text{ B}; V_{WM} = 25.6 \text{ B}; I_{PP} = 14.5 \text{ A}$	DO-214AA, SMB	K•A
LS	SMBJ18	VISH	VS	V _{BR} (I _T = 1.0 mA) = 20.0025.30 B; V _{MM} = 18.0 B; I _{PP} = 18.6 A	DO-214AA, SMB	K•A
LSP	TPSMB33	GS	VS	V _{BB} (I _T =1.0 MA)=29.736.3B; V _{WM} =26.8B; I _{PP} =12.6A	DO-214AA, SMB	K•A
LT	1SMB18AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 20.022.1 \text{ B}; V_{WM} = 29.2 \text{ B}; I_{PP} = 20.5 \text{ A}$	DO-214AA, SMB	K•A
LT	SMBJ18A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 20.0023.30 B; V _{MM} = 18.0B; I _{PP} = 20.5 A	DO-214AA, SMB	K•A
LTC	1SMB18CAT3	ON	٧S	V _{BR} (I _T =1.0 mA)=20.022.1B; V _{WM} =29.2B; I _{PP} =20.5A	DO-214AA, SMB	х∙х
LTP	TPSMB33A	GS	٧S	V _{BP} (I _T = 1.0 mA) = 31.434.7B; V _{WM} = 28.2B; I _{PP} = 13.1A	DO-214AA, SMB	K•A
LU	SMBJ20	VISH	VS	V _{BB} (I _T = 1.0 mA) = 22.2028.10 B; V _{MM} = 20.0 B; I _{PP} = 16.7 A	DO-214AA, SMB	K•A
LUP	TPSMB36	GS	VS	V _{BB} (I _T = 1.0 mA) = 32.439.6B; V _{WM} = 29.1B; I _{PP} = 11.5A	DO-214AA, SMB	K•A
LV	1SMB20AT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 22.224.5B; V _{WM} = 32.4B; I _{PP} = 18.5A	DO-214AA, SMB	K•A
LV	SMBJ20A	VISH	vs	V _{BB} (I _T = 1.0 mA) = 22.2025.50 B; V _{MM} = 20.0 B; I _{PP} = 18.5 A	DO-214AA, SMB	K•A
LVC	1SMB20CAT3	ON	VS	V _{BB} (I _T = 1.0 mA) = 22.224.5B; V _{WM} = 32.4B; I _{PP} = 18.5A	DO-214AA, SMB	х∙х
LVP	TPSMB36A	GS	VS	V _{BB} (I _T = 1.0 mA) = 34.237.8B; V _{WM} = 30.8B; I _{DD} = 12.0A	DO-214AA, SMB	K•A



Код	Типономинал	Б	Ф	Особенности	Корпус	Ц:1•2
LW	SMBJ22	VISH	vs	V _{BR} (I _T = 1.0 mA) = 24.4030.90 B; V _{MM} = 22.0 B; I _{PP} = 15.2 A	DO-214AA, SMB	K•A
LWP	TPSMB39	GS	VS	V _{BR} (I _T = 1.0 mA) = 35.142.9B; V _{WM} = 31.6B; I _{PP} = 10.6A	DO-214AA, SMB	K•A
LX	1SMB22AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 24.426.9 \text{ B}; V_{WM} = 35.5 \text{ B}; I_{pp} = 16.9 \text{ A}$	DO-214AA, SMB	K•A
LX	SMBJ22A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 24.4028.00 B; V _{MM} = 22.0 B; I _{PP} = 16.9 A	DO-214AA, SMB	K•A
LXC	1SMB22CAT3	ON	νS	V _{BR} (I _T = 1.0 mA) = 24.426.9 B; V _{WM} = 35.5 B; I _{pp} = 16.9 A	DO-214AA, SMB	х∙х
LXP	TPSMB39A	GS	٧S	V _{BR} (I _T = 1.0 mA) = 37.141.0 B; V _{WM} = 33.3 B; I _{PP} = 11.1 A	DO-214AA, SMB	K•A
LY	SMBJ24	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 26.7033.80 \text{ B}; V_{MM} = 24.0 \text{ B}; I_{PP} = 14.0 \text{ A}$	DO-214AA, SMB	K•A
LYP	TPSMB43	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 38.747.3 \text{ B}; V_{WM} = 34.8 \text{ B}; I_{pp} = 9.7 \text{ A}$	DO-214AA, SMB	K•A
LZ	1SMB24AT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 26.729.5 \text{ B}; V_{WM} = 38.9 \text{ B}; I_{pp} = 15.4 \text{ A}$	DO-214AA, SMB	K•A
LZ	SMBJ24A	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 26.7030.70 \text{ B}; V_{VMM} = 24.0 \text{ B}; I_{pp} = 15.4 \text{ A}$	DO-214AA, SMB	K•A
LZC	1SMB24CAT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 26.729.5 \text{ B}; V_{WM} = 38.9 \text{ B}; I_{pp} = 15.4 \text{ A}$	DO-214AA, SMB	х∙х
LZP	TPSMB43A	GS	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 40.945.2 \text{ B}; V_{WM} = 36.8 \text{ B}; I_{pp} = 10.1 \text{ A}$	DO-214AA, SMB	K•A
MD	SMBJ26	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 28.9036.80 \text{ B}; V_{VMM} = 26.0 \text{ B}; I_{PP} = 12.4 \text{ A}$	DO-214AA, SMB	K•A
ME	1SMB26AT3	ON	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 28.931.9 \text{ B}; V_{WM} = 42.1 \text{ B}; I_{pp} = 14.2 \text{ A}$	DO-214AA, SMB	K∙A
ME	SMBJ26A	VISH	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 28.9033.20 \text{ B}; V_{MM} = 26.0 \text{ B}; I_{PP} = 14.2 \text{ A}$	DO-214AA, SMB	K•A
MEC	1SMB26CAT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 28.931.9 \text{ B}; V_{WM} = 42.1 \text{ B}; I_{PP} = 14.2 \text{ A}$	DO-214AA, SMB	χ●χ
MF	SMBJ28	VISH	٧S	V _{BR} (I _T = 1.0 mA) = 31.1039.40 B; V _{MM} = 28.0 B; I _{PP} = 12.0 A	DO-214AA, SMB	K•A
MG	1SMB28AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 31.134.4 \text{ B}; V_{WM} = 45.4 \text{ B}; I_{pp} = 13.2 \text{ A}$	DO-214AA, SMB	K•A
MG	SMBJ28A	VISH	٧S	V _{BR} (I _T = 1.0 mA) = 31.1035.80 B; V _{MM} = 28.0 B; I _{PP} = 13.2 A	DO-214AA, SMB	K•A
MGC	1SMB28CAT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 31.134.4 \text{ B}; V_{WM} = 45.4 \text{ B}; I_{PP} = 13.2 \text{ A}$	DO-214AA, SMB	X • X
MH	SMB30	VISH	٧S	V _{BR} (I _T = 1.0 mA) = 33.3042.20 B; V _{MM} = 30.0 B; I _{PP} = 11.2 A	DO-214AC, SMA	K•A
MK	1SMB30AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 33.336.8 B; V _{WM} = 48.4 B; I _{pp} = 12.4 A	DO-214AA, SMB	K•A
MK	SMBJ30A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 33.3038.30 B; V _{MM} = 30.0 B; I _{PP} = 12.4 A	DO-214AA, SMB	K•A
MKC	1SMB30CAT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 33.336.8 B; V _{WM} = 48.4 B; I _{pp} = 12.4 A	DO-214AA, SMB	x•x
ML	SMBJ33	VISH	vs	V _{BR} (I _T = 1.0 mA) = 36.7046.90 B; V _{VM} = 33.0 B; I _{PP} = 10.2 A	DO-214AA, SMB	K•A
MM	1SMB33AT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 36.740.6 B; V _{WM} = 53.3 B; I _{pp} = 11.3 A	DO-214AA, SMB	K•A
MM	SMBJ33A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 36.7042.20 \text{ B}; V_{MM} = 33.0 \text{ B}; I_{PP} = 11.3 \text{ A}$	DO-214AA, SMB	K•A
MMC	1SMB33CAT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 36.740.6 \text{ B}; V_{WM} = 53.3 \text{ B}; I_{PP} = 11.3 \text{ A}$	DO-214AA, SMB	х∙х
MN	SMBJ36	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 40.0050.70 \text{ B}; V_{VMM} = 36.0 \text{ B}; I_{PP} = 9.3 \text{ A}$	DO-214AA, SMB	K•A
MP	1SMB36AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 40.044.2 B; V _{WM} = 58.1 B; I _{pp} = 10.3 A	DO-214AA, SMB	K•A
MP	SMBJ36A	VISH	٧S	V _{BR} (I _T = 1.0 mA) = 40.0046.00 B; V _{MM} = 36.0 B; I _{PP} = 10.3 A	DO-214AA, SMB	K•A
MPC	1SMB36CAT3	ON	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 40.044.2 \text{ B}; V_{WM} = 58.1 \text{ B}; I_{PP} = 10.3 \text{ A}$	DO-214AA, SMB	х∙х
MQ	SMBJ40	VISH	VS	V _{BR} (I _T = 1.0 mA) = 44.4056.30 B; V _{VM} = 40.0 B; I _{PP} = 8.4 A	DO-214AA, SMB	K∙A
MR	1SMB40AT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 44.449.1 \text{ B}; V_{WM} = 64.5 \text{ B}; I_{PP} = 9.3 \text{ A}$	DO-214AA, SMB	K•A
MR	SMBJ40A	VISH	٧S	V _{BR} (I _T = 1.0 mA) = 44.4051.10 B; V _{MM} = 40.0 B; I _{PP} = 9.3 A	DO-214AA, SMB	K•A
MRC	1SMB40CAT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 44.449.1 \text{ B}; V_{WM} = 64.5 \text{ B}; I_{pp} = 9.3 \text{ A}$	DO-214AA, SMB	x•x
MS	SMBJ43	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 47.8060.50 \text{ B}; V_{VMM} = 43.0 \text{ B}; I_{pp} = 7.8 \text{ A}$	DO-214AA, SMB	K•A
MT	1SMB43AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 47.852.8 \text{ B}; V_{WM} = 69.4 \text{ B}; I_{PP} = 8.6 \text{ A}$	DO-214AA, SMB	K•A
MT	SMBJ43A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 47.8054.90 \text{ B}; V_{WM} = 43.0 \text{ B}; I_{pp} = 8.6 \text{ A}$	DO-214AA, SMB	K•A
MTC	1SMB43CAT3	ON	٧S	V _{BR} (I _T = 1.0 mA) = 47.852.8 B; V _{WM} = 69.4 B; I _{PP} = 8.6 A	DO-214AA, SMB	х∙х
MU	SMBJ45	VISH	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 50.0063.30 \text{ B}; V_{VMM} = 45.0 \text{ B}; I_{PP} = 7.5 \text{ A}$	DO-214AA, SMB	K•A
MV	1SMB45AT3	ON	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 50.055.3 \text{ B}; V_{WM} = 72.7 \text{ B}; I_{PP} = 8.3 \text{ A}$	DO-214AA, SMB	K•A
MV	SMBJ45A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 50.0057.50 \text{ B}; V_{VMM} = 45.0 \text{ B}; I_{PP} = 8.3 \text{ A}$	DO-214AA, SMB	K∙A
MVC	1SMB45CAT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 50.055.3 \text{ B}; V_{WM} = 72.7 \text{ B}; I_{pp} = 8.3 \text{ A}$	DO-214AA, SMB	х∙х
MW	SMBJ48	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 53.3067.50 \text{ B}; V_{MM} = 48.0 \text{ B}; I_{PP} = 7.0 \text{ A}$	DO-214AA, SMB	K•A
MX	1SMB48AT3	ON	٧S	V _{BR} (I _T = 1.0 mA) = 53.358.9B; V _{WM} = 77.4B; I _{PP} = 7.7A	DO-214AA, SMB	K∙A
MX	SMBJ48A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 53.3061.30 B; V _{VM} = 48.0 B; I _{PP} = 7.7 A	DO-214AA, SMB	K•A
MXC	1SMB48CAT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 53.358.9B; V _{WM} = 77.4B; I _{PP} = 7.7A	DO-214AA, SMB	x•x
MY	SMBJ51	VISH	vs	V _{BR} (I _T = 1.0 mA) = 56.7071.80 B; V _{MM} = 51.0 B; I _{PP} = 6.6 A	DO-214AA, SMB	K•A
MZ	1SMB51AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 56.762.7B; V _{WM} = 82.4B; I _{PP} = 7.3A	DO-214AA, SMB	K•A
MZ	SMBJ51A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 56.7065.20 B; V _{MM} = 51.0 B; I _{PP} = 7.3 A	DO-214AA, SMB	K•A
MZC	1SMB51CAT3	ON	νs	V _{BR} (I _T = 1.0 mA) = 56.762.7B; V _{WM} = 82.4B; I _{PP} = 7.3A	DO-214AA, SMB	х∙х
ND	SMBJ54	VISH	vs	V _{BR} (I _T = 1.0 mA) = 60.0076.00 B; V _{MM} = 54.0 B; I _{PP} = 6.2 A	DO-214AA, SMB	K•A





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2
NE	1SMB54AT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 60.066.3B; V _{WM} = 87.1B; I _{PP} = 6.9A	DO-214AA, SMB	K•A
NE	SMBJ54A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 60.0069.00 B; V _{MM} = 54.0 B; I _{PP} = 6.9 A	DO-214AA, SMB	K•A
NEC	1SMB54CAT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 60.066.3 \text{B}; V_{WM} = 87.1 \text{B}; I_{pp} = 6.9 \text{A}$	DO-214AA, SMB	х∙х
NF.	SMBJ58	VISH	VS	V _{BR} (I _T = 1.0 mA) = 64.4081.60 B; V _{MM} = 58.0 B; I _{PP} = 5.8 A	DO-214AA, SMB	K•A
NG	1SMB58AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 64.471.2 \text{B}; V_{WM} = 93.6 \text{B}; I_{pp} = 6.4 \text{A}$	DO-214AA, SMB	K•A
NG	SMBJ58A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 64.4074.60 B; V _{MM} = 58.0 B; I _{PP} = 6.4 A	DO-214AA, SMB	K•A
NGC	1SMB58CAT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 64.471.18 \text{ B}; V_{WM} = 93.6 \text{ B}; I_{PP} = 6.4 \text{ A}$	DO-214AA, SMB	K•A
NH	SMBJ60	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 66.7084.50 \text{ B}; V_{MM} = 60.0 \text{ B}; I_{pp} = 5.6 \text{ A}$	DO-214AA, SMB	K•A
NK	1SMB60AT3	ON	VS.	V _{BR} (I _T = 1.0 mA) = 66.773.7B; V _{WM} = 96.8B; I _{PP} = 6.2A	DO-214AA, SMB	K•A
NK	SMBJ60A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 66.7076.70 \text{ B}; V_{MM} = 60.0 \text{ B}; I_{pp} = 6.2 \text{ A}$	DO-214AA, SMB	K•A
NKC	1SMB60CAT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 66.773.72 \text{ B}; V_{WM} = 96.8 \text{ B}; I_{PP} = 6.2 \text{ A}$	DO-214AA, SMB	х∙х
NL	SMBJ64	VISH	VS	V _{BR} (I _T = 1.0 mA) = 71.1090.10 B; V _{MM} = 64.0 B; I _{pp} = 5.3 A	DO-214AA, SMB	K•A
NM	1SMB64AT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 71.178.6B; V _{WM} = 103B; I _{PP} = 5.8 A	DO-214AA, SMB	K•A
NM	SMBJ64A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 71.1081.80 B; V _{MM} = 64.0 B; I _{PP} = 5.8 A	DO-214AA, SMB	K•A
NMC	1SMB64CAT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 71.178.58 \text{ B}; V_{WM} = 103 \text{ B}; I_{PP} = 5.8 \text{ A}$	DO-214AA, SMB	х∙х
NN	SMBJ70	VISH	VS	V _{BB} (I _T = 1.0 mA) = 77.8098.60 B; V _{MM} = 70.0 B; I _{PP} = 4.8 A	DO-214AA, SMB	K•A
NP	1SMB70AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 77.886 \text{B}; V_{WM} = 113 \text{B}; I_{PP} = 5.3 \text{A}$	DO-214AA, SMB	K•A
NP	SMBJ70A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 77.8089.50 B; V _{MM} = 70.0 B; I _{PP} = 5.3 A	DO-214AA, SMB	K∙A
NPC	1SMB70CAT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 77.885.99B; V _{WM} = 113B; I _{PP} = 5.3A	DO-214AA, SMB	х∙х
NQ	SMBJ75	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 83.30106.00 \text{ B}; V_{WM} = 75.0 \text{ B}; I_{pp} = 4.5 \text{ A}$	DO-214AA, SMB	K•A
NR	1SMB75AT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 83.392.1B; V _{MM} = 121B; I _{PP} = 4.9 A	DO-214AA, SMB	K•A
NR	SMBJ75A	VISH	vs	V _{BB} (I _T = 1.0 mA) = 83.3095.80 B; V _{MM} = 75.0B; I _{PP} = 4.9A	DO-214AA, SMB	K•A
NRC	1SMB75CAT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 83.392.07B; V _{WM} = 121B; I _{PP} = 4.9A	DO-214AA, SMB	х∙х
NS	SMBJ78	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 86.70110.00 \text{ B}; V_{MM} = 78.0 \text{ B}; I_{PP} = 4.3 \text{ A}$	DO-214AA, SMB	K•A
NT	1SMB78AT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 86.795.83 B; V _{WM} = 126 B; I _{PP} = 4.7 A	DO-214AA, SMB	K•A
NT	SMBJ78A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 86.7099.70 B; V _{MM} = 78.0 B; I _{PP} = 4.7 A	DO-214AA, SMB	K•A
NTC	1SMB78CAT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 86.795.83 B; V _{WM} = 126 B; I _{PP} = 4.7 A	DO-214AA, SMB	х∙х
NU	SMBJ85	VISH	VS	V _{BB} (I _T = 1.0 mA) = 94.40119.20 B; V _{WM} = 85.0 B; I _{PP} = 3.9 A	DO-214AA, SMB	K•A
NV	1SMB85AT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 94.4104 B; V _{WM} = 137 B; I _{PP} = 4.4 A	DO-214AA, SMB	K•A
NV	SMBJ85A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 94.40108.20 B; V _{WM} = 85.0 B; I _{PP} = 4.4 A	DO-214AA, SMB	K•A
NW	SMBJ90	VISH	VS	V _{BR} (I _T = 1.0 mA) = 100.0126.50 B; V _{WM} = 90.0 B; I _{PP} = 3.8 A	DO-214AA, SMB	K•A
NX	1SMB90AT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 100111 \text{ B}; V_{WM} = 146 \text{ B}; I_{PP} = 4.1 \text{ A}$	DO-214AA, SMB	K•A
NX	SMBJ90A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 100.0115.50 \text{ B}; V_{WM} = 90.0 \text{ B}; I_{PP} = 4.1 \text{ A}$	DO-214AA, SMB	K•A
NY	SMBJ100	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 111.0141.00 \text{ B}; V_{WM} = 100.0 \text{ B}; I_{PP} = 3.4 \text{ A}$	DO-214AA, SMB	K•A
NZ	1SMB100AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 111123 \text{ B}; V_{WM} = 162 \text{ B}; I_{PP} = 3.7 \text{ A}$	DO-214AA, SMB	K•A
NZ	SMBJ100A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 111.0128.00 \text{ B}; V_{WM} = 100.0 \text{ B}; I_{pp} = 3.7 \text{ A}$	DO-214AA, SMB	K•A
PD	SMBJ110	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 122.0154.50 \text{ B}; V_{WM} = 110.0 \text{ B}; I_{pp} = 3.0 \text{ A}$	DO-214AA, SMB	K•A
PE	1SMB110AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 122135 \text{B}; V_{WM} = 177 \text{B}; I_{PP} = 3.4 \text{A}$	DO-214AA, SMB	K•A
PE	SMBJ110A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 122.0140.00 \text{ B}; V_{MM} = 110.0 \text{ B}; I_{PP} = 3.4 \text{ A}$	DO-214AA, SMB	K•A
PF	SMBJ120	VISH	VS	V _{BR} (I _T = 10 mA) = 133.0169.00 B; V _{MM} = 120.0 B; I _{PP} = 2.8 A	DO-214AA, SMB	K•A
PG	1SMB120AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 133147 \text{ B}; V_{WM} = 193 \text{ B}; I_{PP} = 3.1 \text{ A}$	DO-214AA, SMB	K•A
PG	SMBJ120A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 133.0153.00 \text{ B}; V_{WM} = 120.0 \text{ B}; I_{PP} = 3.1 \text{ A}$	DO-214AA, SMB	K•A
PH	SMBJ130	VISH	VS	V _{BR} (I _T = 1.0 mA) = 144.0182.50 B; V _{WM} = 130.0 B; I _{pp} = 2.6 A	DO-214AA, SMB	K•A
PK	1SMB130AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 144159 \text{ B}; V_{WM} = 209 \text{ B}; I_{PP} = 2.9 \text{ A}$	DO-214AA, SMB	K•A
PK	SMBJ130A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 144.0165.50 \text{ B}; V_{WM} = 130.0 \text{ B}; I_{PP} = 2.9 \text{ A}$	DO-214AA, SMB	K•A
PL	SMBJ150	VISH	VS	V _{BR} (I _T = 1.0 MA) = 167.0211.50 B; V _{MM} = 150.0 B; I _{PP} = 2.2 A	DO-214AA, SMB	K∙A
PM	1SMB150AT3	ON	VS	V _{BR} (I _T = 1.0 MA) = 167185B; V _{WM} = 243B; I _{PP} = 2.5A	DO-214AA, SMB	K•A
PM	SMBJ150A	VISH	VS	V _{BR} (I _T = 1.0 MA) = 167.0192.50 B; V _{MM} = 150.0 B; I _{PP} = 2.5 A	DO-214AA, SMB	K•A
PN	SMBJ160	VISH	vs	V _{BR} (I _T = 1.0 MA) = 178.0226.00 B; V _{WM} = 160.0 B; I _{PP} = 2.1 A	DO-214AA, SMB	K•A
PP	1SMB160AT3	ON	vs	V _{BR} (I _T = 1.0 MA) = 178197B; V _{WM} = 259B; I _{PP} = 2.3 A	DO-214AA, SMB	K•A
PR	1SMB170AT3	ON	vs	V _{BR} (I _T = 1.0 MA) = 189209 B; V _{WM} = 275 B; I _{PP} = 2.2 A	DO-214AA, SMB	K•A
QE	1SMA5.0AT3	ON	VS	V _{BR} (I _T = 10.0 mA) = 6.47.0 B; V _{WM} = 9.2 B; I _{PP} = 43.5 A	DO-214AC, SMA	K∙A
QG	1SMA6.0AT3	ON	VS	V _{BR} (I _T = 10.0 mA) = 6.677.37B; V _{WM} = 10.3B; I _{pp} = 38.8A	DO-214AC, SMA	K•A



Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2
QK	1SMA6.5AT3	ON	vs	V _{BR} (I _T = 10.0 mA) = 7.227.98 B; V _{VM} = 11.2 B; I _{PP} = 35.7 A	DO-214AC, SMA	K•A
QM	1SMA7.0AT3	ON	vs	$V_{BR}(I_T = 10.0 \text{ mA}) = 7.788.6 \text{ B}; V_{WM} = 12.0 \text{ B}; I_{pp} = 33.3 \text{ A}$	DO-214AC, SMA	K•A
QP	1SMA7.5AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 8.339.21 B; V _{WM} = 12.9 B; I _{pp} = 31.0 A	DO-214AC, SMA	K•A
QR	1SMA8.0AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 8.899.83 B; V _{WM} = 13.6 B; I _{PP} = 29.4 A	DO-214AC, SMA	K•A
QT	1SMA8.5AT3	ON	νS	V _{BR} (I _T = 1.0 mA) = 9.4410.4B; V _{WM} = 14.4B; I _{pp} = 27.8A	DO-214AC, SMA	K•A
Q٧	1SMA9.0AT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 1011.1 \text{ B}; V_{WM} = 15.4 \text{ B}; I_{PP} = 26.0 \text{ A}$	DO-214AC, SMA	K•A
QX	1SMA10AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 11.112.3 B; V _{WM} = 17.0 B; I _{pp} = 23.5 A	DO-214AC, SMA	K•A
QXC	1SMA10CAT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 11.112.27 \text{ B}; V_{WM} = 17.0 \text{ B}; I_{pp} = 23.5 \text{ A}$	DO-214AC, SMA	χ•χ
QZ	1SMA11AT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 12.213.5 \text{B}; V_{WM} = 18.2 \text{B}; I_{pp} = 22.0 \text{A}$	DO-214AC, SMA	K•A
QZC	1SMA11CAT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 12.213.48 B; V _{VM} = 18.2 B; I _{pp} = 22.0 A	DO-214AC, SMA	х∙х
RA	RGF1A	VISH	dr	$V_R < 50 \text{ B}; I_F < 1 \text{ A}; V_F (I_F = 1 \text{ A}) < 1.3 \text{ B}; C_D = 8.5 \text{ n}\Phi$	DO-214BA	K•A
RB	RGF1B	VISH	dr	$V_R < 100 \text{ B}; I_F < 1 \text{ A}; V_F (I_F = 1 \text{ A}) < 1.3 \text{ B}; C_D = 8.5 \text{ n}\Phi$	DO-214BA	K•A
RD	RGF1D	VISH	dr	$V_R < 200 \text{ B}; I_F < 1 \text{ A}; V_F (I_F = 1 \text{ A}) < 1.3 \text{ B}; C_D = 8.5 \text{ n}\Phi$	DO-214BA	K•A
RD	SMAJ54	VISH	vs	V _{BR} (I _T = 1.0 mA) = 60.073.3 B; V _{WM} = 96.3 B; I _{pp} = 4.2 A	DO-214AC, SMA	K•A
RE	1SMA12AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 13.314.7B; V _{WM} = 19.9B; I _{pp} = 20.1 A	DO-214AC, SMA	K•A
RE	SMAJ54A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 60.066.3 B; V _{WM} = 87.1 B; I _{PP} = 4.6 A	DO-214AC, SMA	K•A
REC	1SMA12CAT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 13.314.7B; V _{WM} = 19.9B; I _{pp} = 20.1 A	DO-214AC, SMA	х∙х
RF	SMAJ58	VISH	vs	V _{BR} (I _T = 1.0 mA) = 64.478.7B; V _{WM} = 103B; I _{PP} = 3.9 A	DO-214AC, SMA	K•A
RG	1SMA13AT3	ON	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 14.415.9 \text{B}; V_{WM} = 21.5 \text{B}; I_{PP} = 18.6 \text{A}$	DO-214AC, SMA	K•A
RG	RGF1G	VISH	dr	V _B <400 B; I _E <1 A; V _E (I _E =1 A)<1.3B; C _D =8.5 пФ	DO-214BA	K•A
RG	SMAJ58A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 64.471.2B; V _{WM} = 93.6B; I _{pp} = 4.3A	DO-214AC, SMA	K•A
RGC	1SMA13CAT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 14.415.92 B; V _{MM} = 21.5 B; I _{PP} = 18.6 A	DO-214AC, SMA	х∙х
RH	SMAJ60	VISH	vs	V _{BR} (I _T = 1.0 mA) = 66.781.5B; V _{WM} = 107B; I _{PP} = 3.7A	DO-214AC, SMA	K•A
RJ	RGF1J	VISH	dr	$V_B < 600 \text{ B}; I_E < 1 \text{ A}; V_E (I_E = 1 \text{ A}) < 1.3 \text{ B}; C_D = 8.5 \text{ n} \Phi$	DO-214BA	K•A
RK	1SMA14AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 15.617.24 B; V _{VM} = 23.2 B; I _{PP} = 17.2 A	DO-214AC, SMA	K•A
RK	RGF1K	VISH	dr	V _B <800 B; I _E <1 A; V _E (I _E =1 A)<1.3 B; C _D =8.5 πΦ	DO-214BA	K•A
RK	SMAJ60A	VISH	vs	V _{BB} (I _T = 1.0 MA) = 6673.7B; V _{WM} = 96.8B; I _{PP} = 4.1A	DO-214AC, SMA	K•A
RKC	1SMA14CAT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 15.617.24 B; V _{MM} = 23.2 B; I _{PP} = 17.2 A	DO-214AC, SMA	x•x
RL	SMAJ64	VISH	vs	V _{BR} (I _T = 1.0 mA) = 71.186.4B; V _{WM} = 114B; I _{PP} = 3.5 A	DO-214AC, SMA	K•A
RM	1SMA15AT3	ON	vs	V _{BR} (I _T = 1.0 MA) = 16.718.5B; V _{WM} = 24.4B; I _{PP} = 16.4A	DO-214AC, SMA	K•A
RM	RGF1M	VISH	dr	V _B <1000 B; I _E < 1A; V _E (I _E =1A)<1.3B; C _D =8.5 пФ	DO-214BA	K•A
RM	SMAJ64A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 71.178.6B; V _{WM} = 103B; I _{PP} = 3.9 A	DO-214AC, SMA	K•A
RMC	1SMA15CAT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 16.718.46 B; V _{MM} = 24.4 B; I _{PP} = 16.4 A	DO-214AC, SMA	х∙х
RN	SMAJ70	VISH	vs	V _{BR} (I _T = 1.0 mA) = 77.895.1B; V _{WM} = 125B; I _{PP} = 3.2 A	DO-214AC, SMA	K•A
RP	1SMA16AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 17.819.7B; V _{WM} = 26.0B; I _{PP} = 15.4A	DO-214AC, SMA	K•A
RP	SMAJ70A	VISH	vs	V _{BB} (I _T = 1.0 mA) = 77.886.0B; V _{MM} = 113B; I _{PP} = 3.5 A	DO-214AC, SMA	K•A
RPBF	MMT05B230T3	ON	TSPD	V _{вв} = 190B; I _{вор} > 50 A; С _т < 75 пФ	DO-214AA, SMB	K•A
RPBG	MMT05B260T3	ON	TSPD	V _{вв} = 240B; I _{pps} > 50 A; С _т < 75 пФ	DO-214AA, SMB	K•A
RPBJ	MMT05B310T3	ON	TSPD	V _{BR} = 280B; I _{ppS} > 50 A; С _Т < 75 пФ	DO-214AA, SMB	K•A
RPC	1SMA16CAT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 17.819.67 B; V _{WM} = 26.0 B; I _{PP} = 15.4 A	DO-214AC, SMA	х∙х
RPDF	MMT10B230T3	ON	TSPD	V _{BR} = 190 B; I _{DDS} > 100 A; C _T < 200 πΦ	DO-214AA, SMB	K•A
RPDG	MMT10B260T3	ON	TSPD		DO-214AA, SMB	K•A
RPDJ	MMT10B310T3	ON		V _{BB} = 280B; I _{BDS} > 100 A; C _T < 200 nΦ	DO-214AA, SMB	K•A
RQ	SMAJ75	VISH	vs	V _{BB} (I _T = 1.0 mA) = 83.3102 B; V _{WM} = 134 B; I _{PP} = 3.0 A	DO-214AC, SMA	K•A
RR	1SMA17AT3	ON	VS	V _{BB} (I _T = 1.0 mA) = 18.920.9B; V _{MM} = 27.6B; I _{PP} = 14.5A	DO-214AC, SMA	K•A
BB	SMAJ75A	VISH	vs	V _{BR} (I _T = 1.0 mA) =83.392.1B; V _{WM} = 121B; I _{PP} = 3.3 A	DO-214AC, SMA	K•A
RRC	1SMA17CAT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 18.920.9B; V _{WM} = 27.6B; I _{PP} = 14.5A	DO-214AC, SMA	X • X
RS	SMAJ78	VISH	vs	V _{BB} (I _T = 1.0 mA) = 86.7106 B; V _{MM} = 139 B; I _{PP} = 2.9 A	DO-214AC, SMA	K•A
RT	1SMA18AT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 2022.1 B; V _{MM} = 29.2 B; I _{PP} = 13.7 A	DO-214AC, SMA	K•A
RT	SMAJ78A	VISH	vs	V _{BR} (I _T = 1.0 mA) = 86.795.8 B; V _{MM} = 126 B; I _{PP} = 2.2 A	DO-214AC, SMA	K•A
RTC	1SMA18CAT3	ON	vs vs	V _{BR} (I _T = 1.0 mA) = 2022.11 B; V _{MM} = 29.2 B; I _{PP} = 13.7 A	DO-214AC, SMA	X•X
A CONTRACTOR OF THE PARTY OF TH			_	V _{BR} (I _T = 1.0 mA) = 94.4115 B; V _{MM} = 151 B; I _{PP} = 2.6 A	DO-214AC, SMA	K•A
RU	SMAJ85	VISH	VS			





Код	Типономинал	6	Φ	Особенности	Kopnyc	Ц: 1•2
RV	SMAJ85A	VISH	VS	V _{BR} (I _T = 1.0 mA) = 94.4104 B; V _{MM} = 137 B; I _{PP} = 2.9 A	DO-214AC, SMA	K•A
RVC	1SMA20CAT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 22.224.54B; V _{WM} = 32.4B; I _{pp} = 12.3A	DO-214AC, SMA	х∙х
RW	SMAJ90	VISH	VS	V _{BR} (I _T = 1.0 mA) = 100122B; V _{WM} = 160B; I _{PP} = 2.5 A	DO-214AC, SMA	K•A
RX	1SMA22AT3	ON	VS.	$V_{BR}(I_T = 1.0 \text{ mA}) = 24.426.9 \text{ B}; V_{WM} = 35.5 \text{ B}; I_{PP} = 11.3 \text{ A}$	DO-214AC, SMA	K•A
RX	SMAJ90A	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 100111 \text{ B}; V_{WM} = 146 \text{ B}; I_{PP} = 2.7 \text{ A}$	DO-214AC, SMA	K•A
RXC	1SMA22CAT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 24.426.97B; V _{WM} = 35.5B; I _{PP} = 11.3A	DO-214AC, SMA	х∙х
RY	SMAJ100	VISH	VS	V _{BR} (I _T = 1.0 mA) = 111136B; V _{WM} = 179B; I _{PP} = 2.2A	DO-214AC, SMA	K•A
RZ	1SMA24AT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 26.729.5 \text{B}; V_{WM} = 38.9 \text{B}; I_{PP} = 10.3 \text{A}$	DO-214AC, SMA	K•A
RZ	SMAJ100A	VISH	VS.	$V_{BR}(I_T = 1.0 \text{ mA}) = 111123 \text{ B}; V_{WM} = 162 \text{ B}; I_{PP} = 2.5 \text{ A}$	DO-214AC, SMA	K•A
RZC	1SMA24CAT3	ON	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 26.729.51 \text{ B}; V_{WM} = 38.9 \text{ B}; I_{pp} = 10.3 \text{ A}$	DO-214AC, SMA	х∙х
S1A	S1A	FAIR	dr	V _R < 50 B; I _F < 1 A; V _F (I _F = 1 A) < 1.1 B	DO-214AC, SMA	K•A
S1A	SMB4001	MCC	dr	$V_R < 50 \text{ B}$; $I_F = 1 \text{ A}$; $V_F (I_F = 1 \text{ A}) < 1.1 \text{ B}$; $C_D = 12 \text{ n}\Phi$	DO-214AA, SMB	K•A
S1B	S1B	FAIR	dr	V _R < 100 B; I _F < 1 A; V _F (I _F = 1 A) < 1.1 B	DO-214AC, SMA	K•A
S1B	SMB4002	MCC	dr	$V_R < 100 \text{ B}; I_F = 1 \text{ A}; V_F (I_F = 1 \text{ A}) < 1.1 \text{ B}; C_D = 12 \text{ n} \Phi$	DO-214AA, SMB	K•A
S1D	S1D	FAIR	dr	$V_B < 200 \text{ B}; I_F < 1 \text{ A}; V_F (I_F = 1 \text{ A}) < 1.1 \text{ B}$	DO-214AC, SMA	K•A
S1D	SMB4003	MCC	dr	V _B < 200 B; I _F = 1 A; V _F (I _F = 1 A) < 1.1 B; C _D = 12 nΦ	DO-214AA, SMB	K•A
S1G	S1G	FAIR	dr	V _B <400 B; I _F <1A; V _F (I _F =1A)<1.1 B	DO-214AC, SMA	K•A
S1G	SMB4004	MCC	dr	$V_B < 400 \text{ B}; I_F = 1 \text{ A}; V_F (I_F = 1 \text{ A}) < 1.1 \text{ B}; C_D = 12 \text{ n}\Phi$	DO-214AA, SMB	K•A
S1J	S1J	FAIR	dr	V _B < 600 B; I _E < 1 A; V _E (I _E = 1 A) < 1.1 B	DO-214AC, SMA	K•A
S1J	SMB4005	MCC	dr	$V_B < 600 \text{ B}; I_E = 1 \text{ A}; V_E (I_E = 1 \text{ A}) < 1.1 \text{ B}; C_D = 12 \text{ n}\Phi$	DO-214AA, SMB	K•A
S1K	S1K	FAIR	dr	V _B < 800 B; I _F < 1 A; V _F (I _F = 1 A) < 1.1 B	DO-214AC, SMA	K•A
S1K	SMB4006	MCC	dr	$V_B < 800 \text{ B}; I_F = 1 \text{ A}; V_F (I_F = 1 \text{ A}) < 1.1 \text{ B}; C_D = 12 \text{ n} \Phi$	DO-214AA, SMB	K•A
S1M	S1M	FAIR	dr	V _B <1000 B; I _F <1 A; V _F (I _F =1 A)<1.1 B	DO-214AC, SMA	K•A
S1M	SMB4007	MCC	dr	V _B < 1000 B; I _E = 1 A; V _E (I _E = 1 A) < 1.1 B; C _D = 12 nΦ	DO-214AA, SMB	K•A
SD	SMAJ110	VISH	vs	V _{BB} (I _T = 1.0 mA) = 122149B; V _{WM} = 196B; I _{PP} = 2.0 A	DO-214AC, SMA	K•A
SE	1SMA26AT3	ON	VS	V _{BB} (I _T = 1.0 mA) = 28.931.9B; V _{WM} = 42.1B; I _{PP} = 9.5A	DO-214AC, SMA	K•A
SE	SMAJ110A	VISH	VS	V _{BB} (I _T = 1.0 mA) = 122135B; V _{WM} = 177B; I _{PP} = 2.3 A	DO-214AC, SMA	K•A
SEC	1SMA26CAT3	ON	VS	V _{BB} (I _T = 1.0 MA) = 28.931.94B; V _{WM} = 42.1B; I _{PP} = 9.5A	DO-214AC, SMA	х∙х
SF	SMAJ120	VISH	vs	V _{BB} (I _T = 1.0 mA) = 133163 B; V _{WM} = 214 B; I _{FP} = 1.9 A	DO-214AC SMA	K•A
SG	1SMA28AT3	ON	vs	V _{BR} (I _T = 1.0 MA) = 31.134.4B; V _{WM} = 45.4B; I _{PP} = 8.8A	DO-214AC SMA	K•A
SG	SMAJ120A	VISH	vs	V _{BR} (I _T = 1.0 MA) = 133147B; V _{WM} = 193B; I _{PP} = 2.0 A	DO-214AC, SMA	K•A
SGC	1SMA28CAT3	ON	vs.	V _{BR} (I _T = 1.0 mA) = 31.134.37B; V _{WM} = 45.4B; I _{PP} = 8.8A	DO-214AC, SMA	х∙х
SH	SMAJ130	VISH	VS	V _{BB} (I _T = 1.0 mA) = 144176B; V _{WM} = 231B; I _{PP} = 1.7A	DO-214AC, SMA	K•A
SK	1SMA30AT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 33.336.8B; V _{WM} = 48.4B; I _{PP} = 8.3A	DO-214AC, SMA	K•A
SK	SMAJ130A	VISH	VS	V _{BB} (I _T = 1.0 mA) = 144159B; V _{WM} = 209B; I _{PP} = 1.9A	DO-214AC, SMA	K•A
SKC	1SMA30CAT3	ON	VS	V _{BB} (I _T = 1.0 mA) = 33.336.81B; V _{WM} = 48.4B; I _{PP} = 8.3A	DO-214AC SMA	x•x
SL	SMAJ150	VISH	vs	V _{BR} (I _T = 1.0 MA) = 167204B; V _{WM} = 268B; I _{PP} = 1.5 A	DO-214AC, SMA	K•A
SM	1SMA33AT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 36.740.6B; V _{MM} = 53.3B; I _{PP} = 7.5A	DO-214AC, SMA	K•A
SM	SMAJ150A	VISH	vs	V _{BB} (I _T = 1.0 mA) = 167185B; V _{WM} = 243B; I _{PP} = 1.6A	DO-214AC, SMA	K•A
SMC	1SMA33CAT3	ON	vs	V _{BB} (I _T = 1.0 MA) = 36.740.56B; V _{WM} = 53.3B; I _{PP} = 7.5A	DO-214AC, SMA	х∙х
SN	SMAJ160	VISH	vs	V _{BB} (I _T = 1.0 MA) = 178218B; V _{WM} = 287B; I _{PP} = 1.4A	DO-214AC, SMA	K•A
SP	1SMA36AT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 4044.2B; V _{MM} = 58.1B; I _{PP} = 6.9A	DO-214AC SMA	K•A
SP	SMAJ160A	VISH	VS	V _{BB} (I _T = 1.0 MA) = 178197B; V _{WM} = 259B; I _{PP} = 1.5 A	DO-214AC, SMA	K•A
SPC	1SMA36CAT3	ON	VS	V _{BB} (I _T = 1.0 MA) = 4044.21B; V _{WM} = 58.1B; I _{PP} = 6.9 A	DO-214AC, SMA	χ∙х
SQ	SMAJ170	VISH	VS	V _{BB} (I _T = 1.0 mA) = 189231 B; V _{WM} = 304 B; I _{PP} = 1.3 A	DO-214AC, SMA	K•A
SR	1SMA40AT3	ON	VS	V _{BB} (I _T = 1.0 MA) = 44.449.1 B; V _{WM} = 64.5 B; I _{PP} = 6.2 A	DO-214AC, SMA	K•A
SR	SMAJ170	VISH	VS	V _{BB} (I _T = 1.0 MA) = 189209B; V _{WM} = 275B; I _{PP} = 1.4 A	DO-214AC, SMA	K•A
SRC	1SMA40CAT3	ON	VS	V _{BB} (I _T = 1.0 MA) = 44.449.07B; V _{MM} = 64.5B; I _{PP} = 6.2A	DO-214AC, SMA	x•x
ST	1SMA43AT3	ON	VS	V _{BR} (I _T = 1.0 mA) = 47.852.8B; V _{WM} = 69.4B; I _{PP} = 5.8A	DO-214AC, SMA	K•A
STC	1SMA43CAT3	ON	vs.	V _{BB} (I _T = 1.0 mA) = 47.852.83 B; V _{WM} = 69.4 B; I _{PP} = 5.8 A	DO-214AC, SMA	X•X
SV	1SMA45AT3	ON	vs	V _{BB} (I _T = 1.0 MA) = 5055.3B; V _{MM} = 72.2B; I _{PP} = 5.5 A	DO-214AC, SMA	K•A
SVC	1SMA45CAT3	ON	VS	V _{BB} (I _T = 1.0 MA) = 5055.3 B; V _{WM} = 72.2 B; I _{PP} = 5.5 A	DO-214AC, SMA	X•X
SX	1SMA48AT3	ON	VS	V _{BB} (I _T = 1.0 MA) = 53.358.9B; V _{WM} = 77.4B; I _{PP} = 5.2A	DO-214AC SMA	K•A
Carl.	DINATURIO	J.	4.0	TBRUT TOWNS GOLD TO SOLUTION TO THE STATE OF STATE	DO LITAO, ONIA	IV-V



Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2
SXC	1SMA48CAT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 53.358.91 B; V _{WM} =77.4 B; I _{FP} = 5.2 A	DO-214AC, SMA	х∙х
SZ	1SMA51AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 56.762.7B; V _{WM} = 82.4B; I _{PP} = 4.9A	DO-214AC, SMA	K•A
SZC	1SMA51CAT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 56.762.67 \text{ B}; V_{WM} = 82.4 \text{ B}; I_{PP} = 4.9 \text{ A}$	DO-214AC, SMA	х∙х
TD	SMAJ5.0C	VISH	νs	$V_{BR}(I_T = 10.0 \text{ mA}) = 6.407.30 \text{ B}; V_{WM} = 9.6 \text{ B}; I_{pp} = 41.6 \text{ A}$	DO-214AC, SMA	х∙х
TE	1SMA54AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 6066.3 B; V _{WM} = 87.1 B; I _{PP} = 4.6 A	DO-214AC, SMA	K•A
TE	SMAJ5.0AC	VISH	٧S	V _{BR} (I _T = 10.0 mA) = 6.47.0 B; V _{WM} = 9.2 B; I _{PP} = 43.5 A	DO-214AC, SMA	χ●χ
TEC	1SMA54CAT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 6066.32 B; V _{WM} = 87.1 B; I _{PP} = 4.6 A	DO-214AC, SMA	х∙х
TF	SMAJ6.0C	VISH	VS	V _{BR} (I _T = 10.0 mA) = 6.678.15 B; V _{WM} = 11.4 B; I _{pp} = 35.1 A	DO-214AC, SMA	х∙х
TG	1SMA58AT3	ON	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 64.471.5 \text{ B}; V_{WM} = 93.6 \text{ B}; I_{PP} = 4.3 \text{ A}$	DO-214AC, SMA	K•A
TG	SMAJ6.0AC	VISH	vs	V _{BR} (I _T = 10.0 mA) = 6.677.37 B; V _{WM} = 10.3 B; I _{PP} = 38.8 A	DO-214AC, SMA	x • x
TGC	1SMA58CAT3	ON	٧S	$V_{BR}(I_T = 1.0 \text{ mA}) = 64.471.5 \text{ B}; V_{WM} = 93.6 \text{ B}; I_{PP} = 4.3 \text{ A}$	DO-214AC, SMA	х∙х
TH	SMAJ6.5C	VISH	vs	V _{BB} (I _T = 10.0 mA) = 7.228.82 B; V _{WM} = 12.3 B; I _{PP} = 32.5 A	DO-214AC, SMA	x•x
TK	1SMA60AT3	ON	VS.	$V_{BR}(I_T = 1.0 \text{ mA}) = 66.773.7 \text{ B}; V_{WM} = 96.8 \text{ B}; I_{PP} = 4.1 \text{ A}$	DO-214AC, SMA	K•A
TK	SMAJ6.5AC	VISH	vs	V _{BB} (I _T = 10.0 mA) = 7.227.98 B; V _{WM} = 11.2 B; I _{PP} = 35.7 A	DO-214AC, SMA	х∙х
TKC	1SMA60CAT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 66.773.72 B; V _{WM} = 96.8 B; I _{PP} = 4.1 A	DO-214AC, SMA	х∙х
TL	SMAJ7.0C	VISH	vs	V _{BR} (I _T = 10.0 mA) = 7.789.51 B; V _{WM} = 13.3 B; I _{PP} = 30.1 A	DO-214AC, SMA	χ●χ
TM	1SMA64AT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 71.178.6B; V _{WM} = 103 B; I _{PP} = 3.9 A	DO-214AC, SMA	K•A
TM	SMAJ7.0AC	VISH	vs	V _{BR} (I _T = 10.0 mA) = 7.788.60 B; V _{WM} = 12.0 B; I _{PP} = 33.3 A	DO-214AC, SMA	x•x
TMC	1SMA64CAT3	ON	vs	V _{BR} (I _T = 1.0 mA) = 71.178.58 B; V _{WM} = 103 B; I _{PP} = 3.9 A	DO-214AC, SMA	x•x
TN	SMAJ7.5C	VISH	vs	$V_{BB}(I_T = 1.0 \text{ mA}) = 8.3310.3 \text{ B}; V_{WM} = 14.3 \text{ B}; I_{pp} = 28.0 \text{ A}$	DO-214AC, SMA	х∙х
TP	1SMA70AT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 77.886B; V _{WM} = 113B; I _{PP} = 3.5 A	DO-214AC, SMA	K•A
TP	SMAJ7.5AC	VISH	vs	V _{BB} (I _T = 1.0 mA) = 8.339.21B; V _{MM} = 12.9B; I _{PP} = 31.0A	DO-214AC, SMA	х∙х
TPC	1SMA70CAT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 77.885.99 B; V _{WM} = 113 B; I _{PP} = 3.5 A	DO-214AC, SMA	х∙х
TQ	SMAJ8.0C	VISH	vs	V _{RR} (I _T = 1.0 mA) = 8.8910.9B; V _{WM} = 15.0B; I _{PP} = 26.5 A	DO-214AC, SMA	x•x
TR	1SMA75AT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 83.392.1B; V _{WM} = 121B; I _{PP} = 3.3 A	DO-214AC, SMA	K•A
TB	SMAJ8.0AC	VISH	vs	V _{BB} (I _T = 1.0 mA) = 8.899.83 B; V _{MM} = 13.6 B; I _{PP} = 29.4 A	DO-214AC, SMA	x•x
TBC	1SMA75CAT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 83.392.1 B; V _{WM} = 121 B; I _{PP} = 3.3 A	DO-214AC, SMA	x•x
TS	1SMA78AT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 86.795.83 B; V _{WM} = 126 B; I _{PP} = 3.2 A	DO-214AC, SMA	K•A
TS	SMAJ8.5C	VISH	vs	V _{BB} (I _T = 1.0 mA) = 9.4411.5B; V _{WM} = 15.9B; I _{PP} = 25.1A	DO-214AC, SMA	x•x
TSC	1SMA78CAT3	ON	vs	V _{BB} (I _T = 1.0 mA) = 86.795.83 B; V _{WM} = 126 B; I _{FP} = 3.2 A	DO-214AC, SMA	x•x
Π	SMAJ8.5AC	VISH	vs	V _{BB} (I _T = 1.0 mA) = 9.44 10.4B; V _{MM} = 14.4B; I _{PP} = 27.7A	DO-214AC, SMA	x•x
TU	SMAJ9.0C	VISH	vs	V _{BB} (I _T = 1.0 mA) = 10.012.2B; V _{MM} = 16.9B; I _{pp} = 23.6A	DO-214AC, SMA	х∙х
TV	SMAJ9.0AC	VISH	vs	V _{BB} (I _T = 1.0 mA) = 10.011.1B; V _{WM} = 15.4B; I _{PP} = 26.0A	DO-214AC, SMA	х∙х
TW	SMAJ10C	VISH	vs	V _{BB} (I _T = 1.0 mA) = 11.113.6B; V _{WM} = 18.8B; I _{pp} = 21.2A	DO-214AC, SMA	χ●χ
TX	SMAJ10AC	VISH	vs	V _{RR} (I _T = 1.0 mA) = 11.112.3B; V _{MM} = 17.0B; I _{PP} = 23.5A	DO-214AC, SMA	х∙х
TY	SMAJ11C	VISH	vs	V _{BB} (I _T = 1.0 mA) = 12.214.9B; V _{MM} = 20.1B; I _{PP} = 20.0A	DO-214AC, SMA	x•x
TZ	SMAJ11AC	VISH	vs	V _{RR} (I _T = 1.0 mA) = 12.213.5B; V _{MM} = 18.2B; I _{DD} = 22.0A	DO-214AC, SMA	x•x
U1A	MURS 105T3	ON	dr	V _B <50 B; I _E = 1 A; V _E (I _E = 1 A) < 0.71 B; t _{BB} < 35 Hc	DO-214AA, SMB	K•A
U1B	MURS110T3	ON	dr	V _B < 100 B; I _F = 1 A; V _F (I _F = 1 A) < 0.71 B; t _{BB} < 35 Hc	DO-214AA, SMB	K•A
U1C	MURS115T3	ON	dr	V _B < 150 B; I _F = 1 A; V _F (I _F = 1 A) < 0.71 B; t _{BB} < 35 Hc	DO-214AA. SMB	K•A
U1D	MURS 120T3	ON	dr	V _B < 200 B; I _F = 1 A; V _F (I _F = 1 A) < 0.71 B; t _{BB} < 35 Hc	DO-214AA, SMB	K•A
U1G	MURS 140T3	ON	dr	V _B < 400 B; I _F = 1 A; V _F (I _F = 1 A) < 1.05 B; t _{BB} < 75 HC	DO-214AA, SMB	K•A
U1J	MURS 160T3	ON	dr	V _B < 600 B; I _E = 1 A; V _E (I _E = 1 A) < 1.05 B; t _{BB} < 75 HC	DO-214AA, SMB	K•A
UA	US1A	GS	fd	V _B = 50 B; I _E = 1 A; C _D = 17 nΦ	DO-214AC, SMA	K•A
UB	US1B	GS	fd	V _B = 100 B; I _F = 1 A; C _D = 17 пФ	DO-214AC, SMA	K•A
UD	SMAJ12C	VISH	vs	V _{RR} (I _T = 1.0 MA) = 13.316.3 B; V _{MM} = 22.0 B; I _{DD} = 18.1 A	DO-214AC, SMA	X•X
UD	USID	GS	fd	V _B = 200 B; I _F = 1 A; C _D = 17 nΦ	DO-214AC, SMA	K•A
UE	SMAJ12AC	VISH	vs	V _{BB} (I _T = 1.0 MA) = 13.314.7B; V _{WM} = 19.9B; I _{PP} = 20.1A	DO-214AC, SMA	X•X
UF	SMAJ13C	VISH	vs	V _{BB} (I _T = 1.0 mA) = 14.417.6B; V _{WM} = 23.8B; I _{DP} = 16.8A	DO-214AC, SMA	X • X
UG	SMAJ13AC	VISH	vs	V _{BR} (I _T = 1.0 mA) = 14.415.9B; V _{WM} = 21.5B; I _{PP} = 18.6A	DO-214AC, SMA	X • X
UG	US1G	GS	fd	V _B =400 B; I _E =1 A; C _D =17 nΦ	DO-214AC, SMA	K•A
	SMAJ14C	VISH	vs	V _{BR} (I _T = 1.0 MA) = 15.619.1 B; V _{WM} = 25.8 B; I _{PP} = 15.5 A	DO-214AC, SMA	X•X
UH						





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2
UK	SMAJ14AC	VISH	VS	V _{BR} (I _T = 1.0 mA) = 15.617.2B; V _{MM} = 23.2B; I _{pp} = 17.2A	DO-214AC, SMA	х∙х
UL	SMAJ15C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 16.720.4B; V_{MM} = 26.9B; I_{PP} = 14.8A$	DO-214AC, SMA	х∙х
UM	SMAJ15AC	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 16.718.5B; V_{MM} = 24.4 B; I_{PP} = 16.4 A$	DO-214AC, SMA	х∙х
UN	SMAJ16C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 17.821.8 \text{ B}; V_{MM} = 28.8 \text{ B}; I_{PP} = 13.8 \text{ A}$	DO-214AC, SMA	χ∙х
UP	SMAJ16AC	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 17.819.7 \text{ B}; V_{WM} = 26.0 \text{ B}; I_{PP} = 15.3 \text{ A}$	DO-214AC, SMA	х∙х
UQ	SMAJ17C	VISH	VS	V _{BR} (I _T = 1.0 mA) = 18.923.1 B; V _{MM} = 30.5 B; I _{PP} = 13.1 A	DO-214AC, SMA	χ∙х
UR	SMAJ17AC	VISH	VS	V _{BR} (I _T = 1.0 mA) = 18.920.9B; V _{WM} = 27.6B; I _{PP} = 14.5A	DO-214AC SMA	х∙х
US	SMAJ18C	VISH	VS	V _{BR} (I _T = 1.0 mA) = 20.024.4B; V _{WM} = 32.2B; I _{PP} = 12.4A	DO-214AC, SMA	х∙х
UT	SMAJ18AC	VISH	VS	V _{BR} (I _T = 1.0 mA) = 20.022.1 B; V _{MM} = 29.2 B; I _{PP} = 13.7 A	DO-214AC, SMA	х∙х
UU	SMAJ20C	VISH	VS	V _{BR} (I _T = 1.0 mA) = 22.227.1B; V _{MM} = 35.8B; I _{PP} = 11.1A	DO-214AC, SMA	х∙х
UV	SMAJ20AC	VISH	VS	V _{BR} (I _T = 1.0 mA) = 22.224.5B; V _{MM} = 32.4B; I _{PP} = 12.3A	DO-214AC, SMA	х∙х
UW	SMAJ22C	VISH	vs	$V_{BB}(I_T = 1.0 \text{ mA}) = 24.429.8 \text{ B}; V_{MM} = 39.4 \text{ B}; I_{PP} = 10.1 \text{ A}$	DO-214AC, SMA	х∙х
UX	SMAJ22AC	VISH	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 24.426.9 \text{ B}; V_{MM} = 35.5 \text{ B}; I_{PP} = 11.2 \text{ A}$	DO-214AC, SMA	х∙х
UY	SMAJ24C	VISH	vs	V _{BR} (I _T = 1.0 mA) = 26.732.6B; V _{MM} = 43.0B; I _{PP} = 9.3A	DO-214AC, SMA	х∙х
UZ	SMAJ24AC	VISH	VS	$V_{BB}(I_T = 1.0 \text{ mA}) = 26.729.5 \text{B}; V_{MM} = 38.9 \text{B}; I_{PP} = 10.3 \text{A}$	DO-214AC, SMA	х∙х
VD	SMAJ26C	VISH	VS	V _{BB} (I _T = 1.0 mA) = 28.931.9B; V _{MM} = 46.6B; I _{PP} = 8.6A	DO-214AC SMA	χ●χ
VE	SMAJ26AC	VISH	VS	V _{BR} (I _T = 1.0 mA) = 28.925.3B; V _{MM} = 42.1B; I _{PP} = 9.5A	DO-214AC SMA	х∙х
VF	SMAJ28C	VISH	VS	V _{BB} (I _T = 1.0 mA) = 31.138.0B; V _{WM} = 50.0B; I _{PP} = 8.0A	DO-214AC SMA	х∙х
VG	SMAJ28AC	VISH	VS	V _{BB} (I _T = 1.0 mA) = 31.134.4B; V _{MM} = 45.4B; I _{PP} = 8.8A	DO-214AC SMA	x•x
VH	SMAJ30C	VISH	vs	V _{BB} (I _T = 1.0 mA) = 33.340.7B; V _{MM} = 53.5B; I _{PP} = 7.5A	DO-214AC SMA	х∙х
VK	SMAJ30AC	VISH	VS	V _{BB} (I _T = 1.0 mA) = 33.336.8B; V _{MM} = 48.4B; I _{PP} = 8.3A	DO-214AC, SMA	х∙х
VL	SMAJ33C	VISH	VS	V _{BB} (I _T = 1.0 mA) = 36.744.9B; V _{MM} = 59.0B; I _{PP} = 6.8A	DO-214AC, SMA	х∙х
VM	SMAJ33AC	VISH	VS	V _{BB} (I _T = 1.0 MA) = 36.740.6B; V _{MM} = 53.3B; I _{PP} = 7.5A	DO-214AC, SMA	х∙х
VN	SMAJ36C	VISH	VS	V _{BB} (I _T = 1.0 MA) = 40.0 48.9B; V _{MM} = 64.3B; I _{PP} = 6.2A	DO-214AC SMA	x•x
VP	SMAJ36AC	VISH	vs	V _{BB} (I _T = 1.0 mA) = 40.044.2B; V _{MM} = 58.1B; I _{PP} = 6.9A	DO-214AC, SMA	x•x
VQ.	SMAJ40C	VISH	VS	V _{BB} (I _T = 1.0 MA) = 44.454.3B; V _{MM} = 71.4B; I _{PP} = 5.6A	DO-214AC, SMA	x•x
VB	SMAJ40AC	VISH	VS	V _{BB} (I _T = 1.0 MA) = 44.449.1 B; V _{MM} = 64.5 B; I _{PP} = 6.2 A	DO-214AC, SMA	x•x
VS	SMAJ43C	VISH	VS	V _{BB} (I _T = 1.0 MA) = 47.858.4B; V _{MM} = 76.7B; I _{PP} = 5.2A	DO-214AC SMA	x•x
VT	SMAJ43AC	VISH	VS	V _{BB} (I _T = 1.0 MA) = 47.852.8B; V _{MM} = 69.4B; I _{PP} = 5.7A	DO-214AC SMA	χ• χ
VU	SMAJ45C	VISH	vs	V _{BB} (I _T = 1.0 MA) = 50.061.1B; V _{MM} = 80.3B; I _{PP} = 5.0A	DO-214AC, SMA	x•x
W	SMAJ45AC	VISH	VS.	V _{BB} (I _T = 1.0 MA) = 50.055.3B; V _{MM} = 72.7B; I _{PP} = 5.5A	DO-214AC, SMA	x•x
VW	SMAJ48C	VISH	VS	V _{BB} (I _T = 1.0 MA) = 53.365.1B; V _{MM} = 85.5B; I _{PP} = 4.7A	DO-214AC, SMA	x•x
VX	SMAJ48AC	VISH	VS	V _{BB} (I _T = 1.0 MA) = 53.358.9B; V _{MM} = 77.4B; I _{PP} = 5.2A	DO-214AC, SMA	χ• χ
VY	SMAJ51C	VISH	VS	V _{BB} (I _T = 1.0 MA) = 56.769.3B; V _{MM} = 91.1B; I _{PP} = 4.4A	DO-214AC, SMA	X•X
VZ	SMAJ51AC	VISH	VS	V _{BB} (I _T = 1.0 MA) = 56.762.7B; V _{MM} = 82.4B; I _{PP} = 4.9A	DO-214AC SMA	X•X
WD	SMAJ54C	VISH	vs vs	V _{BR} (I _T =1.0 MA)=60.073.3B; V _{WM} =96.3B; I _{PP} =4.2A	DO-214AC SMA	x•x
WE	SMAJ54AC	VISH	VS	V _{BP} (I _T = 1.0 MA) = 60.066.3B; V _{MM} = 87.1B; I _{PP} = 4.6A	DO-214AC SMA	x•x
WF	SMAJ58C	VISH	VS.	$V_{BB}(I_T = 1.0 \text{ MA}) = 64.478.7 \text{ B; } V_{VMI} = 103 \text{ B; } I_{PP} = 3.9 \text{ A}$	DO-214AC SMA	x•x
WG	SMAJ58AC	VISH	VS VS	$V_{BB}(I_T = 1.0 \text{ MA}) = 64.471.2 \text{ B}, V_{VM} = 103 \text{ B}, I_{pp} = 3.3 \text{ A}$	DO-214AC SMA	X • X
WH	SMAJ60C	VISH	vs vs	$V_{BB}(I_T = 1.0 \text{ MA}) = 66.781.5B; V_{WM} = 30.0B; I_{PP} = 4.3A$	DO-214AC, SMA	χ• χ
WK	SMAJ60AC	VISH	vs vs		DO-214AC SMA	χ• χ
WL	SMAJ64C	VISH	-	$V_{BR}(I_T = 1.0 \text{ mA}) = 6673.7 \text{ B}; V_{WM} = 96.8 \text{ B}; I_{PP} = 4.1 \text{ A}$ $V_{BR}(I_T = 1.0 \text{ mA}) = 71.186.4 \text{ B}; V_{WM} = 114 \text{ B}; I_{PP} = 3.5 \text{ A}$	DO-214AC SMA	-
WM		VISH	VS			X•X
WN	SMAJ64AC SMAJ70C	VISH	VS	V _{BR} (I _T = 1.0 mA) = 71.178.6B; V _{WM} = 103B; I _{pp} = 3.9 A	DO-214AC, SMA DO-214AC, SMA	X • X
WO	ESSATURE PARTY		VS	V _{BR} (I _T = 1.0 mA) = 77.895.1 B; V _{MM} = 125B; I _{PP} = 3.2 A		x•x K•A
WP	BZX284-B2V4	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 2.35 2.45 B; Z _{ZT} < 100 O m	SOD-110	
WP	BZX284-B2V7	PHIL	dz	V _z (I _{zT} = 5 mA) = 2.65 2.75 B; Z _{zT} < 100 O m	SOD-110	K•A
3.000	SMAJ70AC		VS d=	V _{BR} (I _T = 1.0 mA) = 77.886.0B; V _{MM} = 113B; I _{PP} = 3.5 A	DO-214AC, SMA	x•x K•A
WQ	BZX284-B3V0	PHIL	dz	V _z (I _{ZT} =5 MA) = 2.943.06 B; Z _{ZT} < 95 OM	SOD-110	-
WQ	SMAJ75C	VISH	VS	V _{BR} (I _T = 1.0 mA) = 83.3102 B; V _{MM} = 134 B; I _{PP} = 3.0 A	DO-214AC, SMA	χ•χ
WR	BZX284-B3V3	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 3.233.37 B; Z _{ZT} < 95 Om	SOD-110	K•A
WR	SMAJ75AC	VISH	VS	V _{BR} (I _T = 1.0 mA) = 83.392.1 B; V _{WM} = 121 B; I _{PP} = 3.3 A	DO-214AC, SMA	X • X
WS	BZX284-B3V6	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 3.533.67 B; Z _{ZT} < 90 Om	SOD-110	K•A
WS	SMAJ78C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ MA}) = 86.7106 \text{ B}; V_{MM} = 139 \text{ B}; I_{PP} = 2.9 \text{ A}$	DO-214AC SMA	X • X



Код	Типономинал	Б	Φ	Особенности	Корпус	Ц: 1•2
WT	BZX284-B3V9	PHIL	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 3.823.98 \text{ B}; Z_{ZT} < 90 \text{ Om}$	SOD-110	K∙A
NT	SMAJ78AC	VISH	vs	V _{BR} (I _T = 1.0 mA) = 86.795.8 B; V _{WM} = 126 B; I _{PP} = 2.2 A	DO-214AC, SMA	х∙х
WU	BZX284-B4V3	PHIL	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 4.214.39 \text{ B}; Z_{ZT} < 90 \text{ Om}$	SOD-110	K•A
WU	SMAJ85C	VISH	vs	V _{BR} (I _T = 1.0 mA) = 94.4115 B; V _{WM} = 151 B; I _{pp} = 2.6 A	DO-214AC, SMA	х∙х
WV	BZX284-B4V7	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 4.614.79 \text{ B}; Z_{ZT} < 80 \text{ Om}$	SOD-110	K∙A
WV	SMAJ85AC	VISH	vs	V _{BR} (I _T =1.0 mA)=94.4104 B; V _{WM} =137 B; I _{PP} =2.9 A	DO-214AC, SMA	χ•χ
WW	BZX284-B5V1	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 5.05.2 \text{ B}; Z_{ZT} \le 60 \text{ Om}$	SOD-110	K•A
WW	SMAJ90C	VISH	vs	$V_{BR}(I_T = 1.0 \text{ mA}) = 100122 \text{ B}; V_{WM} = 160 \text{ B}; I_{pp} = 2.5 \text{ A}$	DO-214AC, SMA	х∙х
WX	BZX284-B5V6	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 5.495.71 \text{ B}; Z_{ZT} < 40 \text{ Om}$	SOD-110	K∙A
WX	SMAJ90AC	VISH	vs	$V_{BB}(I_T = 1.0 \text{ mA}) = 100111 \text{ B; } V_{WM} = 146 \text{ B; } I_{PP} = 2.7 \text{ A}$	DO-214AC, SMA	x•x
WY	BZX284-B6V2	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 6.086.32 \text{ B}; Z_{ZT} < 10 \text{ Cm}$	SOD-110	K∙A
WY	SMAJ100C	VISH	vs	V _{BR} (I _T = 1.0 mA) = 111136 B; V _{WM} = 179 B; I _{PP} = 2.2 A	DO-214AC, SMA	х∙х
WZ	BZX284-B6V8	PHIL	dz	$V_z(I_{zT} = 5 \text{ mA}) = 6.666.94 \text{ B}; Z_{zT} < 15 \text{ Om}$	SOD-110	K•A
WZ	SMAJ100AC	VISH	vs	V _{BB} (I _T = 1.0 mA) = 111123 B; V _{VM} = 162 B; I _{PP} = 2.5 A	DO-214AC, SMA	х∙х
XA	BZX284-B7V5	PHIL	dz	$V_2(I_{2T} = 5 \text{ mA}) = 7.357.65 \text{ B}; Z_{2T} < 10 \text{ Om}$	SOD-110	K•A
XB	BZX284-B8V2	PHIL	dz	$V_2(I_{2T} = 5 \text{ mA}) = 8.048.36 \text{ B}; Z_{2T} < 10 \text{ Om}$	SOD-110	K•A
XC	BZX284-B9V1	PHIL	dz	$V_2(I_{2T} = 5 \text{ mA}) = 8.929.28 \text{ B}; Z_{2T} < 10 \text{ Om}$	SOD-110	K•A
XD	BZX284-B10	PHIL	dz	V ₂ (I ₂₇ =5 mA) = 9.810.2B; Z ₂₇ < 10 Om	SOD-110	K•A
XD	SMAJ110C	VISH	vs	V _{BR} (I _T = 1.0 mA) = 122149 B; V _{WM} = 196 B; I _{PP} = 2.0 A	DO-214AC, SMA	х∙х
XE	BZX284-B11	PHIL	dz	V _Z (I _{ZZ} = 5 mA) = 10.811.2B; Z _{ZZ} < 10 Om	SOD-110	K•A
XE	SMAJ110AC	VISH	vs	V _{RR} (I _T = 1.0 mA) = 122135 B; V _{MM} = 177 B; I _{PP} = 2.3 A	DO-214AC, SMA	х∙х
XF	BZX284-B12	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 11.812.2B; Z _{ZT} < 10 Om	SOD-110	K•A
XF	SMAJ120C	VISH	vs	V _{BB} (I _T = 1.0 mA) = 133163 B; V _{WM} = 214 B; I _{PP} = 1.9 A	DO-214AC, SMA	х•х
XG	BZX284-B13	PHIL	dz	$V_{z}(I_{zT} = 5 \text{ mA}) = 12.713.3 \text{ B; } Z_{zT} < 10 \text{ OM}$	SOD-110	K•A
XG	SMAJ120AC	VISH	VS	V _{BB} (I _T = 1.0 MA) = 133147 B; V _{WM} = 193 B; I _{PP} = 2.0 A	DO-214AC, SMA	X•X
XH	BZX284-B15	PHIL	dz	$V_2(I_{2T} = 5 \text{ mA}) = 14.715.3 \text{ B; } Z_{2T} < 15 \text{ Om}$	SOD-110	K•A
XH	SMAJ130C	VISH	VS	V _{RR} (I _T = 1.0 MA) = 144176 B; V _{MM} = 231 B; I _{PP} = 1.7 A	DO-214AC, SMA	X•X
XI	BZX284-B16	PHIL	dz	V ₂ (I _{2T} = 5 mA) = 15.716.3B; Z _{2T} < 20 Om	SOD-110	K•A
XJ	BZX284-B18	PHIL	dz	$V_2(I_{2T} = 5 \text{ MA}) = 17.618.4 \text{ B}; Z_{2T} < 20 \text{ CM}$	SOD-110	K•A
XK	BZX284-B20	PHIL	dz	V ₇ (I _{2T} = 5 MA) = 19.620.4B; Z _{2T} < 20 OM	SOD-110	K•A
XK	SMAJ130AC	VISH	VS	V _{BB} (I _T = 1.0 mA) = 144159 B; V _{WM} = 209 B; I _{PP} = 1.9 A	DO-214AC, SMA	X•X
XL	BZX284-B22	PHIL	dz	V _T (I _{TT} = 5 mA) = 21.622.4B; Z _{TT} < 25 Om	SOD-110	K•A
XL	SMAJ150C	VISH	VS.	V _{BR} (I _T = 1.0 mA) = 167204 B; V _{WM} = 268 B; I _{PP} = 1.5 A	DO-214AC, SMA	X•X
XM	BZX284-B24	PHIL	dz	V _F (I _{TT} = 5 mA) = 23.524.5 B; Z _{TT} < 30 Om	SOD-110	K•A
XM	SMAJ150AC	VISH	-		DO-214AC. SMA	100
XN		PHIL	VS	V _{BR} (I _T = 1.0 mA) = 167185 B; V _{WM} = 243 B; I _{PP} = 1.6 A	SOD-110	χ•χ
XN	BZX284-B27 SMAJ160C	VISH	dz	V _z (I _{zT} = 5mA) = 26.527.5 B; Z _{zT} < 40 Om	DO-214AC, SMA	K•A x•x
XO			vs	V _{BR} (I _T = 1.0 MA) = 178218 B; V _{WM} = 287 B; I _{PP} = 1.4 A		
XP	BZX284-B30	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 29.430.6B; Z _{ZT} < 40 Om	SOD-110	K•A
XΡ	BZX284-B33	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 32.333.7B; Z _{ZT} < 40 Om	SOD-110	K∙A
	SMAJ160AC	VISH	VS	V _{BR} (I _T = 1.0 mA) = 178197 B; V _{WM} = 259 B; I _{PP} = 1.5 A	DO-214AC, SMA	X • X
XQ	BZX284-B36	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 35.336.7B; Z _{ZT} < 60 Om	SOD-110	K•A
XQ	SMAJ170C	VISH	VS	V _{BR} (I _T = 1.0 mA) = 189231 B; V _{VM} = 304 B; I _{PP} = 1.3 A	DO-214AC, SMA	X•X
XR	BZX284-B39	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 38.239.8 \text{ B}; Z_{ZT} < 75 \text{ Om}$	SOD-110	K•A
XR	SMAJ170C	VISH	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 189209 \text{ B}; V_{VMM} = 275 \text{ B}; I_{pp} = 1.4 \text{ A}$	DO-214AC, SMA	х∙х
XS	BZX284-B43	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 42.143.9 \text{ B}; Z_{ZT} < 80 \text{ Om}$	SOD-110	K•A
XT	BZX284-B47	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 46.147.9 \text{ B}; Z_{ZT} < 90 \text{ Om}$	SOD-110	K•A
XU	BZX284-B51	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 50.052.0 \text{ B}; Z_{ZT} < 110 \text{ Om}$	SOD-110	K•A
ΧV	BZX284-B56	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 54.957.1 \text{ B}; Z_{ZT} < 120 \text{ Om}$	SOD-110	K•A
XW	BZX284-B62	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 60.863.2 \text{ B}; Z_{ZT} < 140 \text{ Om}$	SOD-110	K∙A
XX	BZX284-B68	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 66.669.4 \text{ B}; Z_{ZT} < 160 \text{ Om}$	SOD-110	K•A
XY	BZX284-B75	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 73.576.5 \text{ B}; Z_{ZT} < 175 \text{ Om}$	SOD-110	K•A
YO	BZX284-C2V4	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 2.22.8 \text{ B}; Z_{ZT} < 100 \text{ Om}$	SOD-110	K∙A
YP	BZX284-C2V7	PHIL	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 2.52.9 \text{ B}; Z_{ZT} < 100 \text{ Om}$	SOD-110	K•A





Код	Типономинал	6	Φ	Особенности	Корпус	Ц:1•2
YQ	BZX284-C3V0	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 2.83.2 B; Z _{ZT} < 95 Om	SOD-110	K•A
YR	BZX284-C3V3	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 3.13.5 B; Z _{ZT} < 95 Om	SOD-110	K•A
YS	BZX284-C3V6	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 3.43.8 B; Z _{ZT} < 90 Om	SOD-110	K•A
YΤ	BZX284-C3V9	PHIL	dz	$V_Z(I_{Z1} = 5 \text{ mA}) = 3.74.1 \text{ B; } Z_{Z1} \le 90 \text{ Om}$	SOD-110	K•A
YU	BZX284-C4V3	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 44.6 \text{ B}; Z_{ZT} < 90 \text{ Om}$	SOD-110	K•A
ΥV	BZX284-C4V7	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 4.45 \text{ B}; Z_{ZT} < 80 \text{ Om}$	SOD-110	K•A
YW	BZX284-C5V1	PHIL	dz	$V_Z(I_{ZI} = 5 \text{ mA}) = 4.85.4 \text{ B}; Z_{ZI} < 60 \text{ Om}$	SOD-110	K•A
YX	BZX284-C5V6	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 5.26 \text{ B}; Z_{ZT} < 40 \text{ Om}$	SOD-110	K∙A
YY	BZX284-C6V2	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 5.86.6 \text{ B}; Z_{ZT} \le 10 \text{ Om}$	SOD-110	K•A
YZ	BZX284-C6V8	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 6.47.2 \text{ B}; Z_{ZT} \le 15 \text{ Om}$	SOD-110	K•A
Z100	U2Z100	TOSH	dz	$V_Z(I_{ZT}=3 \text{ mA})=90110 \text{ B}; Z_{ZT}(I_{ZT}=3 \text{ mA})<300 \text{ Om}$	DO-214AA, SMB	K∙A
Z12	U2Z12	TOSH	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 10.813.2 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 300 \text{ m}$	DO-214AA, SMB	K•A
Z13	U2Z13	TOSH	dz	$V_z(I_{ZT} = 10 \text{ mA}) = 11.714.3 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 300 \text{ m}$	DO-214AA, SMB	K•A
Z15	U2Z15	TOSH	dz	V _Z (I _{ZT} = 10 mA) = 13.516.5 B; Z _{ZT} (I _{ZT} = 10 mA) < 30 Om	DO-214AA, SMB	K•A
Z16	U2Z16	TOSH	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 14.417.6 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 30 \text{ Om}$	DO-214AA, SMB	K•A
Z18	U2Z18	TOSH	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 16.219.8 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 30 \text{ Om}$	DO-214AA, SMB	K∙A
Z20	U2Z20	TOSH	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 18.022.0 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 30 \text{ Om}$	DO-214AA, SMB	K•A
Z22	U2Z22	TOSH	dz	$V_z(I_{ZT} = 10 \text{ mA}) = 19.824.2 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 30 \text{ Om}$	DO-214AA, SMB	K•A
Z24	U2Z24	TOSH	dz	$V_z(I_{ZT} = 10 \text{ mA}) = 21.626.4 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 300 \text{ m}$	DO-214AA, SMB	K∙A
Z27	U2Z27	TOSH	dz	$V_z(I_{ZT} = 10 \text{ mA}) = 24.329.7 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 30 \text{ Om}$	DO-214AA, SMB	K•A
Z30	U2Z30	TOSH	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 27.033.0 \text{ B}; Z_{ZT}(I_{ZT} = 10 \text{ mA}) < 300 \text{ m}$	DO-214AA, SMB	K•A
Z33	U2Z33	TOSH	dz	$V_z(I_{zT} = 10 \text{ mA}) = 29.736.3 \text{ B}; Z_{zT}(I_{zT} = 10 \text{ mA}) < 300 \text{ m}$	DO-214AA, SMB	K•A
Z36	U2Z36	TOSH	dz	$V_Z(I_{ZT} = 9 \text{ mA}) = 32.439.6 \text{ B}; Z_{ZT}(I_{ZT} = 9 \text{ mA}) < 30 \text{ Om}$	DO-214AA, SMB	K∙A
Z43	U2Z43	TOSH	dz	$V_Z(I_{ZT} = 7 \text{ mA}) = 38.747.3 \text{ B}; Z_{ZT}(I_{ZT} = 7 \text{ mA}) < 40 \text{ Om}$	DO-214AA, SMB	K•A
Z47	U2Z47	TOSH	dz	$V_Z(I_{ZT}=6 \text{ mA})=42.351.7 \text{ B}; Z_{ZT}(I_{ZT}=6 \text{ mA})<65 \text{ Om}$	DO-214AA, SMB	K•A
Z51	U2Z51	TOSH	dz	$V_Z(I_{ZT}=6 \text{ mA})=45.956.1 \text{ B}; Z_{ZT}(I_{ZT}=6 \text{ mA})<65 \text{ Om}$	DO-214AA, SMB	K•A
Z68	U2Z68	TOSH	dz	$V_Z(I_{ZT}=4 \text{ mA})=61.274.8 \text{ B}; Z_{ZT}(I_{ZT}=4 \text{ mA})<1200 \text{ m}$	DO-214AA, SMB	K•A
Z75	U2Z75	TOSH	dz	$V_Z(I_{ZT}=4 \text{ mA})=67.582.5 \text{ B}; Z_{ZT}(I_{ZT}=4 \text{ mA})<150 \text{ Om}$	DO-214AA, SMB	K•A
Z82	U2Z82	TOSH	dz	$V_z(I_{ZT}=3 \text{ mA})=73.890.2 \text{ B}; Z_{ZT}(I_{ZT}=3 \text{ mA})<1700 \text{ m}$	DO-214AA, SMB	K•A
ZA	BZX284-C7V5	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 77.9 \text{ B}; Z_{ZT} < 10 \text{ Om}$	SOD-110	K•A
ZB	BZX284-C8V2	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 7.78.7 \text{ B; } Z_{ZT} \le 10 \text{ Om}$	SOD-110	K•A
ZC	BZX284-C9V1	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 8.59.6 \text{ B}; Z_{ZT} < 10 \text{ Om}$	SOD-110	K•A
ZD	BZX284-C10	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 9.410.6 B; Z _{ZT} < 10 Om	SOD-110	K•A
ZE	BZX284-C11	PHIL	dz	V _Z (I _{ZT} = 5 мА) = 10.411.6 В; Z _{ZT} < 10 Ом	SOD-110	K•A
ZF	BZX284-C12	PHIL	dz	$V_Z (I_{ZT} = 5 \text{ mA}) = 11.412.7 \text{ B}; Z_{ZT} < 10 \text{ Om}$	SOD-110	K∙A
ZG	BZX284-C13	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 12.414.1 B; Z _{ZT} < 10 Om	SOD-110	K∙A
ZH	BZX284-C15	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 13.815.6 B; Z _{ZT} < 15 Om	SOD-110	K•A
ZHK	SM2Z5V1	STM	dz	$V_z = 5.1B$; $P_S = 2BT$	DO-214AC, SMA	K•A
ZHK	SMAZ5V1	VISH	dz	$V_Z(I_Z=100 \text{ mA})=4.85.4 \text{ B}; Z_{ZT}=5.0 \text{ Om}$	DO-214AC, SMA	K∙A
ZHL	SM2Z5V6	STM	dz	V _Z = 5.6B; P _S = 2B _T	DO-214AC, SMA	K•A
ZHL	SMAZ5V6	VISH	dz	V _Z (I _Z = 100 mA) = 5.26.0 B; Z _{ZT} = 2.0 Om	DO-214AC, SMA	K•A
ZHN	SMAZ6V2	VISH	dz	V _Z (I _Z = 100 mA) = 5.86.6 B; Z _{ZT} = 2.0 Om	DO-214AC, SMA	K•A
ZHO	SMAZ6V8	VISH	dz	V _Z (I _Z = 100 mA) = 6.47.21 B; Z _{ZT} = 2.0 Om	DO-214AC, SMA	K•A
ZHQ	SMAZ7V5	VISH	dz	$V_Z(I_Z = 100 \text{ mA}) = 7.07.9 \text{ B}; Z_{ZT} = 2.0 \text{ Om}$	DO-214AC, SMA	K•A
ZHR	SMAZ8V2	VISH	dz	$V_Z(I_Z=100 \text{ mA})=7.78.7 \text{ B}; Z_{ZT}=2.0 \text{ Om}$	DO-214AC, SMA	K∙A
ZHT	SMAZ9V1	VISH	dz	V _Z (I _Z =50 mA) = 8.59.6 B; Z _{ZT} = 4.0 Om	DO-214AC, SMA	K•A
ZHU	SMAZ10	VISH	dz	V _Z (I _Z = 50 mA) = 9.410.6 B; Z _{ZT} = 4.0 Om	DO-214AC, SMA	K∙A
ZHW	SM2Z12	STM	dz	$V_z = 12.0B; P_S = 2BT$	DO-214AC, SMA	K•A
ZHW	SMAZ12	VISH	dz	$V_Z(I_Z=50 \text{ mA})=11.412.7 \text{ B}; Z_{ZT}=7.0 \text{ Om}$	DO-214AC, SMA	K•A
ZHZ	SMAZ15	VISH	dz	V _Z (I _Z =50 mA) = 13.815.6 B; Z _{ZT} = 10 Om	DO-214AC, SMA	K•A
ZI	BZX284-C16	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 15.317.1 B; Z _{ZT} < 20 Om	SOD-110	K∙A
ZJ	BZX284-C18	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 16.819.1 \text{ B}; Z_{ZT} < 20 \text{ Cm}$	SOD-110	K•A
ZJA	SMAZ16	VISH	dz	V _Z (I _Z = 25 mA) = 15.3 17.1 B; Z _{ZT} = 15 Om	DO-214AC, SMA	K•A



Код	Типономинал	Б	Φ	Особенности	Корпус	Ц: 1•2
ZJF	SM2Z18	STM	dz	Vz=18.0B; Ps=2BT	DO-214AC, SMA	K•A
ZJF	SMAZ18	VISH	dz	V _Z (I _Z = 25 mA) = 16.819.1 B; Z _{ZT} = 15 Om	DO-214AC, SMA	K•A
ZJG	SMAZ20	VISH	dz	V _z (I _z =25 mA)=18.821.2B; Z _{zT} =150m	DO-214AC, SMA	K•A
ZJK	SMAZ22	VISH	dz	$V_z(I_z = 25 \text{ mA}) = 20.823.3 \text{ B}; Z_{zT} = 150 \text{ m}$	DO-214AC, SMA	K•A
ZJL	SMAZ24	VISH	dz	V _Z (I _Z =25 mA)=22.825.6B; Z _{ZT} =150m	DO-214AC, SMA	K•A
ZJN	SMAZ27	VISH	dz	V _Z (I _Z =25 mA)=25.128.9B; Z _{ZT} =150m	DO-214AC, SMA	K•A
ZJQ	SM2Z30	STM	dz	V _Z =30.0 B; P _S =2 B _T	DO-214AC, SMA	K•A
ZJQ	SMAZ30	VISH	dz	$V_Z(I_Z=25 \text{ mA})=2832 \text{ B}; Z_{ZI}=15 \text{ Om}$	DO-214AC, SMA	K•A
ZJR	SMAZ33	VISH	dz	$V_z(I_z=25 \text{ mA})=3135 \text{ B}; Z_{zz}=150 \text{ m}$	DO-214AC, SMA	K•A
ZJS	SMAZ36	VISH	dz	$V_z(I_z = 10 \text{ mA}) = 3438 \text{ B}; Z_{zz} = 40 \text{ Om}$	DO-214AC, SMA	K•A
ZJT	SMAZ39	VISH	dz	$V_z(I_z = 10 \text{ mA}) = 3741 \text{ B}; Z_{zz} = 40 \text{ Om}$	DO-214AC, SMA	K•A
ZJV	SMAZ47	VISH	dz	$V_z(I_z = 10 \text{ mA}) = 4450 \text{ B}; Z_{zz} = 45 \text{ Om}$	DO-214AC, SMA	K•A
ZK	BZX284-C20	PHIL	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 18.821.2 \text{ B}; Z_{ZT} < 20 \text{ Om}$	SOD-110	K•A
ZKM	SMAZ68	VISH	dz	V _Z (I _Z = 10 mA) = 6472 B; Z _{ZI} = 80 Om	DO-214AC, SMA	K•A
ZKQ	SMAZ100	VISH	dz	V _Z (I _Z = 5.0 мA) = 94106 B; Z _{ZT} = 200 Ом	DO-214AC, SMA	K•A
ZKR	SM2Z150	STM	dz	Vz=150B;Ps=2Br	DO-214AC, SMA	K•A
ZKR	SMAZ150	VISH	dz	V _Z (I _Z =5.0 mA) = 138156B; Z _{ZT} =300 Om	DO-214AC, SMA	K∙A
ZKW	SMAZ200	VISH	dz	$V_z(I_z=5.0 \text{ mA})=188212 \text{B}; Z_{zz}=3500 \text{m}$	DO-214AC, SMA	K•A
ZL	BZX284-C22	PHIL	dz	$V_z(I_{zT} = 5 \text{ mA}) = 21.622.4 \text{ B}; Z_{zT} < 25 \text{ Om}$	SOD-110	K•A
ZLGP	TPSMB20A	GS	VS	$V_{BR}(I_T = 1.0 \text{ mA}) = 19.021.0 \text{ B}; V_{WM} = 17.1 \text{ B}; I_{pp} = 21.7 \text{ A}$	DO-214AA, SMB	K•A
ZM	BZX284-C24	PHIL	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 22.823.3 \text{ B}; Z_{ZT} < 30 \text{ Om}$	SOD-110	K•A
ZN	BZX284-C27	PHIL	dz	$V_z(I_{ZT} = 5\text{mA}) = 25.128.9 \text{ B}; Z_{ZT} < 40 \text{ Om}$	SOD-110	K•A
ZO	BZX284-C30	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 2832 \text{ B}; Z_{ZT} < 40 \text{ Om}$	SOD-110	K•A
ZP	BZX284-C33	PHIL	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 3135 \text{ B}; Z_{ZT} < 400 \text{ m}$	SOD-110	K•A
ZQ	BZX284-C36	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 3438 \text{ B}; Z_{ZT} < 60 \text{ Cm}$	SOD-110	K•A
ZR	BZX284-C39	PHIL	dz	$V_Z(I_{ZT}=5 \text{ mA})=3741 \text{ B}; Z_{ZT}<750 \text{ m}$	SOD-110	K•A
ZS	BZX284-C43	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 4046 \text{ B}; Z_{ZT} < 80 \text{ Cm}$	SOD-110	K•A
ZT	BZX284-C47	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 4450 \text{ B}; Z_{ZT} < 90 \text{ Om}$	SOD-110	K•A
ZU	BZX284-C51	PHIL	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 4854 \text{ B}; Z_{ZT} < 110 \text{ Om}$	SOD-110	K•A
ZV	BZX284-C56	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 5260 \text{ B}; Z_{ZT} < 1200 \text{ m}$	SOD-110	K•A
ZW	BZX284-C62	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 5866 B; Z _{ZT} < 140 Om	SOD-110	K•A
ZX	BZX284-C68	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 6472 \text{ B}; Z_{ZT} < 160 \text{ Om}$	SOD-110	K•A
ZY	BZX284-C75	PHIL	dz	$V_z (I_{ZT} = 5 \text{ mA}) = 7079 \text{ B}; Z_{ZT} < 175 \text{ Om}$	SOD-110	K•A

SOD123/323, DO215/216

Код	Типономинал	6	ф	Особенности	Корпус	L‡1•2
40	ZLLS400	ZETEX	shd	V _B <40 B; I _F <0.52 A; V _F (I _F =0.4 A)<0.5 B; I _B <10 mkA; C _D <15 nΦ	SOD-323, SC-76	K•A
46	BAT46J	STM	shd	$V_B < 100 \text{ B}; I_F < 150 \text{ mA}; V_F (I_F = 10 \text{ mA}) < 0.45 \text{ mB}; C_D = 10 \text{ n}\Phi$	SOD-323, SC-76	K•A
86	BAT54J	STM	shd	$V_R < 30 \text{ B}; I_F < 300 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 0.9 \text{ B}; I_R < 1 \text{ mKA}; C_D < 10 \text{ n}\Phi; t_{BR} < 5 \text{ HC}$	SOD-323, SC-76	K • A
02	GDZ2V0B	VISH	dz	V _Z =2.0 B; Z _{ZT} (I _Z =5mA)=100 Om	SOD-323, SC-76	K • A
1 (кра)	BB669	INF	var	V _R <30 B; I _F <20 мA; I _R <0.01 мкА; С _{1 B} =5161.5 пФ; С _{28 B} =2.52.9	SOD-323, SC-76	K • A
12	GDZ2V2B	VISH	dz	V _Z =2.2B; Z _{ZT} (I _Z =5mA)=100 Om	SOD-323, SC-76	K • A
1B	MA2J111	PAN	di	V _B <80 B; I _F <100 mA; V _F (I _F =100 mA)<1.2 B; t _{RB} <3 HC	SOD-323, SC-76	K • A
1C	MA2J112	PAN	di	$V_R < 40 \text{ B}; I_F < 200 \text{ mA}; V_F (I_F = 200 \text{ mA}) < 1.1 \text{ B}; t_{BB} < 10 \text{ Hz}$	SOD-323, SC-76	K • A
1D	MA2J113	PAN	di	$V_R < 80 \text{ B}; I_F < 200 \text{ mA}; V_F (I_F = 200 \text{ mA}) < 1.1 \text{ B}; t_{PR} < 10 \text{ Hz}$	SOD-323, SC-76	K • A
1E	MA2J114	PAN	dr	V _R <150 B; I _F <200 mA; V _F (I _F =200 mA)<1.2 B	SOD-323, SC-76	K • A
1F	MA2J115	PAN	dr	V _E <200 B; I _E <200 mA; V _E (I _E =200 mA)<1.2 B	SOD-323, SC-76	K • A
1H	MA2J116	PAN	dl	V _R <40 B; I _F <100 mA; V _F (I _F =100 mA)<1.2 B; t _{RR} <100 Hc	SOD-323, SC-76	K • A
1P	CMDZ18L	CSI	dz	$V_Z(I_{ZT}=0.5 \text{ mA}) = 18 \text{ B}; P_D \le 250 \text{ mB} \text{T}$	SOD-323, SC-76	K • A
2	BB419	SIEM	var	$V_R < 28 \text{ B; } I_F < 20 \text{ mA; } I_R < 0.02 \text{ mkA; } C_{3B} = 2632 \text{ n\Phi; } C_{3B} / C_{25B} = 56.5$	SOD-123	K • A
2 (бел)	BB439	INF	var	V _B >28 B; I _B (V _B =28 B)<0.02 мкА; С _{2B} =31.537.5 пФ; С _{2SB} =4.36 пФ	SOD-323, SC-76	K • A
2 (син)	BAR64-03W	INF	pin	$V_R \le 150 \text{ B}; I_F \le 100 \text{ mA}; V_F (I_F = 50 \text{ mA}) \le 1.1 \text{ B}; C_D \le 0.35 \text{ n}\Phi$	SOD-323, SC-76	K•A
22	GDZ2V4B	VISH	dz	Vz = 2.4 B; ZzT (Iz = 5mA) = 100 Om	SOD-323, SC-76	K • A
20B	1PMT5920B	ON	dz	$V_Z(I_{ZT}=60.5 \text{ mA})=6.2 \text{B}; Z_{ZT}=2.0 \text{ Om}$	DO-216AA, PWRM	K • A
21B	1PMT5921B	ON	dz	$V_Z(I_{ZT}=55.1 \text{ mA})=6.8 \text{B}; Z_{ZT}=2.5 \text{ Om}$	DO-216AA, PWRM	K • A
22B	1PMT5922B	ON	dz	$V_Z(I_{ZT}=50.0 \text{ mA}) = 7.5 \text{B}; Z_{ZT}=3.0 \text{ Om}$	DO-216AA, PWRM	K • A
23B	1PMT5923B	ON	dz	V _Z (I _{ZT} =45.7 mA) = 8.2B; Z _{ZT} =3.50m	DO-216AA, PWRM	K • A
24B	1PMT5924B	ON	dz	$V_Z(I_{Z1}=41.2 \text{ mA})=9.1 \text{ B; } Z_{Z1}=4.0 \text{ Om}$	DO-216AA, PWRM	K • A
25B	1PMT5925B	ON	dz	$V_Z(I_{ZT} = 37.5 \text{ mA}) = 10 \text{ B}; Z_{ZT} = 4.5 \text{ Om}$	DO-216AA, PWRM	K • A
27B	1PMT5927B	ON	dz	$V_Z(I_{ZT} = 31.2 \text{ mA}) = 12 \text{ B}; Z_{ZT} = 6.5 \text{ Om}$	DO-216AA, PWRM	K • A
29B	1PMT5929B	ON	dz	V _Z (I _{ZT} = 25.0 mA) = 15 B; Z _{ZT} = 9.0 Om	DO-216AA, PWRM	K•A
2P	CMDZ20L	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 20 \text{ B}; P_D < 250 \text{ mBT}$	SOD-323, SC-76	K • A
3 (бел)	BAT60A	INF	shd	$V_R < 10B$; $I_F < 3A$; $V_F (I_F = 10 \text{ mA}) < 0.15B$; $I_R < 2.6 \text{ mA}$; $C_D = 20 \text{ m}$	SOD-323, SC-76	K • A
32	GDZ2V7B	VISH	dz	V _Z =2.7B; Z _{ZT} (I _Z =5mA)=110 Om	SOD-323, SC-76	K • A
30B	1PMT5930B	ON	dz	V _Z (I _{ZT} = 23.4 mA) = 16 B; Z _{ZT} = 10 Cm	DO-216AA, PWRM	K • A
31B	1PMT5931B	ON	dz	V _Z (I _{ZT} = 20.8 mA) = 18 B; Z _{ZT} = 12 Om	DO-216AA, PWRM	K • A
33B	1PMT5933B	ON	dz	$V_Z(I_{ZT} = 17.0 \text{ mA}) = 22 \text{ B}; Z_{ZT} = 17.5 \text{ Om}$	DO-216AA, PWRM	K • A
34B	1PMT5934B	ON	dz	V _Z (I _{ZT} = 15.6 mA) = 24 B; Z _{ZT} = 19 Om	DO-216AA, PWRM	K • A
35B	1PMT5935B	ON	dz	$V_Z(I_{ZT} = 13.9 \text{ mA}) = 27 \text{ B}; Z_{ZT} = 23 \text{ Om}$	DO-216AA, PWRM	K • A
36B	1PMT5936B	ON	dz	$V_Z(I_{ZT} = 12.5 \text{ mA}) = 30 \text{ B}; Z_{ZT} = 28 \text{ Om}$	DO-216AA, PWRM	K • A
39B	1PMT5939B	ON	dz	$V_Z(I_{ZT} = 9.6 \text{ mA}) = 39 \text{ B}; Z_{ZT} = 45 \text{ Om}$	DO-216AA, PWRM	K • A
3P	CMDZ22L	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 22 \text{ B; } P_D \le 250 \text{ mBT}$	SOD-323, SC-76	K • A
4 (бел)	BAS140W	INF	shd	$V_R < 40 \text{ B}; I_F < 120 \text{ mA}; V_F (I_F = 40 \text{ mA}) < 1 \text{ B}; I_R < 1.0 \text{ mkA}; C_D < 5 \text{ n}\Phi$	SOD-323, SC-76	K•A
4 (жел)	BB644	INF	var	V _R <30 B; I _F <20 мA; I _R <0.01 мкA; С _{1 B} =3944.5 пФ; С _{28 B} =2.42.75	SOD-323, SC-76	K•A
42	GDZ3V0B	VISH	dz	$V_z = 3.0 \text{ B}; Z_{zT}(I_z = 5 \text{ mA}) = 120 \text{ Om}$	SOD-323, SC-76	K • A
41B	1PMT5941B	ON	dz	$V_Z(I_{ZT}=8.0 \text{ mA})=47 \text{ B}; Z_{ZT}=67 \text{ Om}$	DO-216AA, PWRM	K • A
4K	MMSD3000T1	MOT	di	$V_R < 30B$; $I_F < 200 \text{ mA}$; $V_F (I_F = 10 \text{ mA}) < 0.95B$; $C_D < 2 \text{ m}$; $t_{RR} < 3 \text{ HC}$	SOD-123	K • A
4P	CMDZ24L	CSI	dz	$V_Z(I_{ZT}=0.5 \text{ mA}) = 24 \text{ B}; P_0 \le 250 \text{ mBT}$	SOD-323, SC-76	K•A
5 (бел)	BBY53-03W	INF	var	$V_R \le 6 \text{ B}; I_F \le 20 \text{ mA}; I_R \le 0.01 \text{ mKA}; C_{1B} = 4.85.8 \text{ n}\Phi; C_{3B} = 1.853.1 \text{ n}\Phi$	SOD-323, SC-76	K • A
5 (к ра)	BBY57-03W	INF	var	$V_R \le 10 \text{ B}; I_F \le 20 \text{ mA}; I_R \le 0.001 \text{ m/sA}; C_{1B} = 16.518.6 \text{ n}\Phi; C_{4B} = 45.5 \text{ n}\Phi$	SOD-323, SC-76	K•A
5 (син)	BAT60B	INF	shd	$V_B < 10 \text{ B}; I_F < 3 \text{ A}; V_F (I_F = 10 \text{ mA}) = 0.24 \text{ B}; I_B = 10 \text{ mKA}; C_D = 25 \text{ n}\Phi$	SOD-323, SC-76	K+A
52	GDZ3V3B	VISH	dz	V _Z =3.3 B; Z _{ZT} (I _Z =5 mA) = 1210 Om	SOD-323, SC-76	K•
5D	MMSD914T1	ON	di	V _B <100 B; I _F <200 mA; V _F (I _F =10 mA)<1 B; C ₀ <4πΦ	SOD-123	K•A
51	MMSD4148T1	ON	di	$V_B < 100 \text{ B}; I_E < 200 \text{ mA}; V_E (I_E = 10 \text{ mA}) < 1 \text{ B}; C_D < 4 \pi \Phi$	SOD-123	K • A





Код	Типономинал	Б	Φ	Особенности	Корпус	Ц:1•2
5P	CMDZ27L	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 27 \text{ B}; P_D < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
6 (кра)	BBY56-03W	INF	var	$V_R < 10 \text{ B}; I_F < 20 \text{ mA}; I_R < 0.005 \text{ mrA}; C_{1B} = 3743 \text{ n}\Phi; C_{4B} = 12.1 \text{ n}\Phi$	SOD-323, SC-76	K•A
62	GDZ3V6B	VISH	dz	$V_Z = 3.6 \text{ B}; Z_{ZT} (I_Z = 5 \text{ mA}) = 100 \text{ Om}$	SOD-323, SC-76	K•A
6P	CMDZ30L	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 30 \text{ B; } P_D \le 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
6S	MMSD71RKT1	ON	di	$V_R < 80 \text{ B}; I_F < 200 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 1.2 \text{ B}; C_D < 2 \text{ n}\Phi$	SOD-123	K•A
7 (бел)	BAS170W	INF	shd	$V_R < 70 \text{ B}; I_F < 70 \text{ mA}; V_F (I_F = 15 \text{ mA}) < 1.0 \text{ B}; I_R < 0.1 \text{ mkA}; C_D < 2.0 \text{ n}\Phi$	SOD-323, SC-76	K•A
7 (бел)	BBY55-03W	INF	var	$V_R < 16B$; $I_F < 20$ mA; $I_R < 0.003$ m/sA; $C_{1B} = 17.519.6$ m Φ ; $C_{10B} = 5.56.5$ m Φ	SOD-323, SC-76	K • A
72	GDZ3V9B	VISH	dz	$V_2 = 3.9 \text{ B}; Z_{ZT} (I_2 = 5 \text{ mA}) = 100 \text{ Om}$	SOD-323, SC-76	K ∙ A
76	BAS70J	STM	shd	$V_B < 70 \text{ B}; I_F < 70 \text{ mA}; V_F (I_F = 1 \text{ mA}) < 0.41 \text{ B}; I_B < 0.1 \text{ mkA}; C_D < 2.0 \text{ n}\Phi$	SOD-323, SC-76	K•A
7N	CMDZ1L8	CSI	dz	$V_Z(I_{ZT}=0.5 \text{ mA})=1.8 \text{B}; P_D<250 \text{ mB} \text{T}$	SOD-323, SC-76	K • A
7P	CMDZ33L	CSI	dz	$V_Z(I_{ZT}=0.5 \text{ mA}) = 33 \text{ B; } P_D \le 250 \text{ mB} \text{T}$	SOD-323, SC-76	K •A
8 (жел)	BBY58-03W	INF	var	$V_R < 10B$; $I_F < 20 \text{ mA}$; $I_R < 0.01 \text{ mkA}$; $C_{1B} = 17.519.3 \text{ n}\Phi$; $C_{4B} = 5.56.6 \text{ n}\Phi$	SOD-323, SC-76	K • A
82	GDZ4V3B	VISH	dz	$V_2 = 4.3 \text{ B}; Z_{ZT} (I_2 = 5 \text{ mA}) = 100 \text{ Om}$	SOD-323, SC-76	K•A
8N	CMDZ2L0	CSI	dz	$V_2(I_{27}=0.5 \text{ mA})=2.0 \text{B}; P_0 < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
8P	CMDZ36L	CSI	dz	$V_2(I_{ZT} = 0.5 \text{ mA}) = 36 \text{ B}; P_D \le 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
92	GDZ4V7B	VISH	dz	V _z =4.7 B; Z _{ZI} (I _z =5 mA) = 100 Om	SOD-323, SC-76	K•A
913B	1PMT5913BT3	MOT	dz	$V_2(I_{27} = 113.6 \text{ mA}) = 3.3 \text{ B}; Z_{27} = 10.0 \text{ Om}$	DO-216AA, PWRM	K.A
914B	1PMT5914BT3	MOT	dz	V _z (I _{ZT} = 104.2 mA) = 3.6 B; Z _{ZT} = 9.0 Om	DO-216AA, PWRM	
915B	1PMT5915BT3	MOT	dz	V ₂ (I _{2T} =96.1 mA) = 3.9 B; Z _{2T} =7.5 Om	DO-216AA, PWRM	K•A
916B	1PMT5916BT3	MOT	dz	V _z (I _{z1} =87.2 mA) = 4.3 B; Z _{z1} =6.0 Om	DO-216AA, PWRM	
917B	1PMT5917BT3	MOT	dz	V ₂ (I _{2T} = 79.8 mA) = 4.7 B; Z _{2T} = 5.0 Om	DO-216AA, PWRM	1000
918B	1PMT5918BT3	MOT	dz	V ₂ (I _{2T} = 73.5 mA) = 5.1 B; Z _{2T} = 4.0 Om	DO-216AA, PWRM	
919B	1PMT5919BT3	MOT	dz	V ₂ (I _{2T} = 66.9 mA) = 5.6 B; Z _{2T} = 2.0 Om	DO-216AA, PWRM	
920B	1PMT5920BT3	MOT	dz	V _Z (I _{ZT} = 60.5 mA) = 6.2 B; Z _{ZT} = 2.0 Om	DO-216AA, PWRM	
921B	1PMT5921BT3	MOT	dz	$V_2(I_{ZT} = 55.1 \text{ mA}) = 6.8 \text{ B; } Z_{ZT} = 2.5 \text{ Om}$	DO-216AA, PWRM	
922B	1PMT5922BT3	MOT	dz	$V_2(I_{2T} = 50.0 \text{ mA}) = 7.5 \text{ B; } Z_{2T} = 3.0 \text{ Om}$	DO-216AA, PWRM	
923B	1PMT5923BT3	MOT	dz	V ₂ (I _{ZT} = 45.7 mA) = 8.2 B; Z _{ZT} = 3.5 Om	DO-216AA, PWRM	
924B	1PMT5924BT3	MOT	dz	V ₂ (I _{2T} = 41.2 mA) = 9.1 B; Z _{2T} = 4.0 Om	DO-216AA, PWRM	1.5
925B	1PMT5925BT3	MOT	dz	V _Z (I _{ZT} = 37.5 mA) = 10 B; Z _{ZT} = 4.5 Om	DO-216AA, PWRM	
926B	1PMT5926BT3	MOT	dz	V ₂ (I _{2T} = 34.1 mA) = 11 B; Z _{2T} = 5.5 Om	DO-216AA, PWRM	
927B	1PMT5927BT3	MOT	dz	V ₂ (I ₂₇ = 31.2mA) = 12 B; Z ₂₇ = 6.5 Om	DO-216AA, PWRM	
928B	1PMT5928BT3	MOT	dz	V ₂ (I _{2T} = 28.8 mA) = 13 B; Z _{2T} = 7.0 Om	DO-216AA, PWRM	
929B	1PMT5929BT3	MOT	dz	V ₇ (I ₇₇ = 25.0 mA) = 15 B; Z ₇₇ = 9.0 Om	DO-216AA, PWRM	
930B	1PMT5930BT3	MOT	dz	V ₂ (I _{2T} = 23.4 mA) = 16 B; Z _{2T} = 10 Om	DO-216AA, PWRM	
931B	1PMT5931BT3	MOT	dz	V ₂ (I _{2T} = 20.8 mA) = 18 B; Z _{2T} = 12 Om	DO-216AA, PWRM	
932B	1PMT5932BT3	MOT	dz	$V_7(I_{77} = 18.7 \text{ mA}) = 20 \text{ B; } Z_{77} = 14.0 \text{ m}$	DO-216AA, PWRM	
933B	1PMT5933BT3	MOT	dz	V ₂ (I _{ZT} = 17.0 mA) = 22 B; Z _{ZT} = 17.5 Om	DO-216AA, PWRM	
934B	1PMT5934BT3	MOT	dz	V ₂ (I _{2T} = 15.6 mA) = 24 B; Z _{2T} = 19.0 m	DO-216AA, PWRM	
935B	1PMT5935BT3	MOT	dz	V _Z (I _{ZT} = 13.5 mM ₂ = 24 B, Z _{ZT} = 15 GM V _Z (I _{ZT} = 13.9 mA) = 27 B; Z _{ZT} = 23 Om	DO-216AA, PWRM	
936B	1PMT5936BT3	MOT	dz	V ₂ (I _{2T} = 12.5 mA) = 30 B; Z _{2T} = 26 Om	DO-216AA, PWRM	1835 35
937B	1PMT5937BT3	MOT	dz	V ₇ (I _{2T} = 11.4 mA) = 33 B; Z _{7T} = 33 Om	DO-216AA, PWRM	
938B	1PMT5938BT3	MOT	dz	V ₂ (I _{2T} = 10.4 mA) = 36 B; Z _{2T} = 38 Om	DO-216AA, PWRM	
939B	1PMT5939BT3	MOT	dz	$V_2(I_{27} = 16.9 \text{ mA}) = 39 \text{ B; } Z_{27} = 35 \text{ GM}$	DO-216AA, PWRM	
940B	1PMT5940BT3	MOT	dz	V _Z (I _{ZT} = 8.7 mA) = 43 B; Z _{ZT} = 53 Om	DO-216AA, PWRM	
940B 941B	1PMT5940BT3	MOT	dz	$V_Z(I_{ZT}=8.7 \text{ MA}) = 43 \text{ B; } Z_{ZT}=33 \text{ GM}$ $V_Z(I_{ZT}=8.0 \text{ MA}) = 47 \text{ B; } Z_{ZT}=67 \text{ GM}$	DO-216AA, PWRM	1000
941B	1PMT5941BT3	MOT	dz	$V_Z(I_{ZT}=8.0 \text{ MA})=47 \text{ B; } Z_{ZT}=57 \text{ OM}$ $V_Z(I_{ZT}=7.3 \text{ MA})=51 \text{ B; } Z_{ZT}=70 \text{ OM}$	DO-216AA, PWRM	
942B 943B	1PMT5942BT3	MOT	dz	$V_Z(I_{ZT} = 7.3 \text{ MA}) = 51 \text{ B; } Z_{ZT} = 70 \text{ OM}$ $V_Z(I_{ZT} = 6.7 \text{ MA}) = 56 \text{ B; } Z_{ZT} = 86 \text{ OM}$	DO-216AA, PWRM	
943B 944B	1PMT5943BT3	MOT	dz	$V_Z(I_{ZT}=6.7 \text{ MA}) = 50 \text{ B; } Z_{ZT}=80 \text{ CM}$ $V_Z(I_{ZT}=6.0 \text{ MA}) = 62 \text{ B; } Z_{ZT}=100 \text{ CM}$	DO-216AA, PWRM	
945B	1PMT5944BT3	MOT	dz	$V_Z(I_{ZT} = 6.0 \text{ MA}) = 62 \text{ B; } Z_{ZT} = 100 \text{ CM}$ $V_Z(I_{ZT} = 5.5 \text{ MA}) = 68 \text{ B; } Z_{ZT} = 120 \text{ CM}$	DO-216AA, PWRM	
945B		0.000	1000			100
30000	1PMT5946BT3	MOT	dz	V _Z (I _{ZT} = 5.0 mA) = 75 B; Z _{ZT} = 140 Om	DO-216AA, PWRM	
947B	1PMT5947BT3	MOT	dz	V _Z (I _{ZT} = 4.6 mA) = 82 B; Z _{ZT} = 160 Om	DO-216AA, PWRM	
948B	1PMT5948BT3	MOT	dz	$V_Z(I_{ZT}=4.1 \text{ mA}) = 91 \text{ B; } Z_{ZT}=200 \text{ Om}$	DO-216AA, PWRM	ı K•A



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Код	Типономинал	6	Ф	Особенности	Корпус	Ц:1•2
9N	CMDZ2L2	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 2.2 \text{B}; P_D < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
9P	CMDZ39L	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 39 \text{B}; P_D \le 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
A	1SS355	ROHM	di	V_R <80 B; I_F <225 mA; V_F (I_F =100 mA)<1.2 B; I_R <0.1 mkA; t_{PR} <4 hc	SOD-323, SC-76	K•A
Α	BAT14098	SIEM	shd	$V_R < 4B$; $I_F < 90$ mA; $V_F (I_F = 10$ mA) < 0.55 B; $C_D < 0.35$ $\Pi\Phi$	SOD-123	K•A
A	BA597	INF	pin	$V_R > 50 B$; $I_F < 100 mA$; $V_F (I_F = 100 mA) = 0.9 B$; $I_R < 0.02 mkA$	SOD-323, SC-76	K•A
A1	MMSZ10T1	ON	dz	$V_Z(I_{ZT}=5 \text{ mA}) = 9.510.5 \text{ B}; I_R < 0.1 \text{ m/sA}$	SOD-123	K•A
A2	1N4148W	VIS	sd	V _B =75 B; I _F =150 мА; P _D =400 мВт; t _{RR} <4нс	SOD-123	K•A
A2	BA592	PHIL	dtv	$V_R < 35 B$; $I_F < 10 mA$; $V_F (I_F = 100 mA) < 1.0 B$; $I_R < 0.02 m kA$	SOD-323, SC-76	K•A
A2	BB208-03	PHIL	var	$V_B > 10B$; $I_B(V_B = 10B) < 0.01$ mKA; $C_{1B} = 19.923.2$ n Φ ; $C_{7.5B} = 4.55.4$ n Φ	SOD-323, SC-76	K∙A
A2	MMSZ11T1	ON	dz	$V_Z(I_{ZT}=5 \text{ mA}) = 10.4511.55 \text{ B}; I_R < 0.1 \text{ mKA}$	SOD-123	K•A
A3	1N4448W	VIS	sd	V _R =75 B; I _F =150 мА; P _D =500 мВт; t _{RR} <4 нс	SOD-123	K•A
A3	BAP64-03	PHIL	pin	$V_B > 175 \text{ B}; I_F < 100 \text{ mA}; V_F (I_F = 50 \text{ mA}) < 1.1 \text{ B}; I_B < 0.1 \text{ mKA}$	SOD-323, SC-76	K•A
A3	MMSZ12T1	ON	dz	$V_Z(I_{Z1}=5 \text{ mA}) = 11.412.6 \text{ B}; I_R < 0.1 \text{ mKA}$	SOD-123	K•A
A4	1N4150W	VIS	sd	V _B <50 B; I _E =400 mA; P _D =410 mBT; t _{BB} <4 hc	SOD-123	K•A
A4	1N4150W	WTE	sd	V _R <50 В; I _E =400 мА; P _D =410 мВт; t _{RR} <4нс	SOD-123	K•A
A4	MMSZ13T1	ON	dz	V _Z (I _{ZT} = 5 mA) = 12.3513.65 B; I _S < 0.05 mrA	SOD-123	K◆A
A5	1N4151W	VIS	sd	V _B <75 B; I _F =500 mA; P _D =410 mBr; t _{SB} <2 hc	SOD-123	K•A
A5	1N4151W	WTE	sd	V _B <75 B; I _E =300 mA; P _D =500 mBT; t _{BB} <2 hc	SOD-123	K•A
A5	BAP51-03	PHIL	pin	V _B >50 B; I _E <50 mA; V _E (I _E =50 mA)<1.1 B; I _B <1 mKA	SOD-323, SC-76	K•A
A5	MMSZ15T1	ON	dz	V _Z (I _{ZT} =5 mA) = 14.2515.75 B; I _B < 0.05 mkA	SOD-123	K•A
A6	BAS16D	GS	di	V _B <75 B; I _F <250 мA; V _F (I _F =150 мA)<1.25 B; I _B <50 мкA; C _D <2 пФ; t _{BB} <6 нс	SOD-123	K•A
A6	BAS16D	VISH	di	$V_B < 75B$; $I_E < 250$ mA; $V_E (I_E = 150$ mA) < 1.25 B; $I_B < 50$ mrA; $C_D < 2$ n Φ ; $t_{BB} < 6$ Hz	SOD-123	K•A
A6	BAS16WS	GS	di	$V_B < 75B$; $I_F < 250$ mA; $V_F (I_F = 150$ mA) $< 1.25B$; $I_B < 50$ mKA; $C_D < 2$ n Φ ; $t_{BB} < 6$ hc	SOD-323, SC-76	K•A
A6	BAS316	PHIL	fd	$V_B < 85B$; $I_E < 250$ mA; $V_E (I_E = 50$ mA) $< 1.0B$; $C_D < 1.5$ n Φ ; $t_{BB} < 4$ Hc	SOD-323, SC-76	K∙A
A8	BAP50-03	PHIL	pin	V _B >50 B; I _E <50 mA; V _E (I _E =50 mA)<1.1 B; I _B <0.1 mkA	SOD-323, SC-76	K•A
A8	BAV19W	VISH	di	V _B <100 B; I _E <250 мA; V _E (I _E =100 мA)<1 B; I _B <0.1 мкA; C _D =1.5 пФ; t _{BB} <50 нс	SOD-123	K•A
A8	BAV19W	DIODS	di	V _B < 100 B; I _F < 250 мА; V _E (I _F = 100 мА) < 1 B; C _D < 5 пФ; t _{BB} < 50 нс	SOD-123	K•A
8A	BAV19W	WTE	di	V _B < 100 B; I _C < 400 мА; V _E (I _C = 100 мА) < 1 B; C _D < 5 пФ; t _{BB} < 50 нс	SOD-123	K•A
A8	BAV19W	TSC	di	V _B < 100 B; I _E < 400 мА; V _E (I _E = 100 мА) < 1 B; C _D < 5 пФ; t _{BB} < 50 нс	SOD-123	K•A
A8	BAV19W	MCC	di	V _B < 100 B; I _E < 400 мА; V _E (I _E = 100 мА) < 1 B; C _D < 5 пФ; t _{BB} < 50 нс	SOD-123	K•A
A80	BAV20W	WTE	di	V _B <150 B; I _E <400 мА; V _E (I _E = 100 мА)<1 B; C _D <5 пФ; t _{BB} <50 нс	SOD-123	K•A
A82	BAV21W	WTE	di	$V_B < 200 \text{ B; } I_F < 400 \text{ mA; } V_F (I_F = 100 \text{ mA}) < 1 \text{ B; } C_D < 5 \text{ n}\Phi; t_{BB} < 50 \text{ Hz}$	SOD-123	K∙A
A9	BAV20W	VISH	di	$V_B < 150 \text{ B}; I_F < 250 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 1 \text{ B}; I_R < 0.1 \text{ m/A}; C_D = 1.5 \text{ n}\Phi; t_{RR} < 50 \text{ HC}$	SOD-123	K•A
AA	BAV21W	VISH	di	$V_B < 200 \text{ B}; I_F < 250 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 1 \text{ B}; I_B < 0.1 \text{ m/A}; C_D = 1.5 \text{ n}\Phi; t_{BB} < 50 \text{ HC}$	SOD-123	K•A
AA	ZMV829A	ZETEX	var	$V_B < 25 B$; $I_F < 200 MA$; $I_B < 0.02 MKA$; $C_{2B} = 7.389.02 n\Phi$; $C_{2B}/C_{20B} = 4.35.8$	SOD-323, SC-76	K•A
AB	ZMV830A	ZETEX	var	$V_B < 25 B$; $I_F < 200 MA$; $I_B < 0.02 MKA$; $C_{2B} = 911 m\Phi$; $C_{2B}/C_{20B} = 4.56.0$	SOD-323, SC-76	K•A
AC	ZMV831A	ZETEX	var	$V_B < 25 \text{ B; } I_c < 200 \text{ mA; } I_B < 0.02 \text{ mrA; } C_{2B} = 13.516.5 \text{ n}\Phi; C_{2B}/C_{20B} = 4.56.0$	SOD-323, SC-76	K∙A
AD	ZMV832A	ZETEX	var	$V_R < 25 \text{ B; } I_F < 200 \text{ MA; } I_R < 0.02 \text{ MKA; } C_{2B} = 19.824.2 \text{ m} \Phi; C_{2B}/C_{20B} = 56.5$	SOD-323, SC-76	K•A
AE	ZMV833A	ZETEX	var	$V_R < 25 \text{ B; } I_F < 200 \text{ MA; } I_R < 0.02 \text{ M/KA; } C_{2B} = 29.736.3 \text{ m/D; } C_{2B}/C_{20B} = 56.5$	SOD-323, SC-76	K•A
AF	ZMV834A	ZETEX	var	V _R <25 В; I _F < 200 мА; I _R < 0.02 мкА; С _{2 В} = 42.351.7 пФ; С _{2 В} /С _{20 В} = 56.5	SOD-323, SC-76	K•A
AG	ZMV835A	ZETEX	var	$V_R < 25 B$; $I_F < 200 MA$; $I_R < 0.02 MKA$; $C_{2B} = 61.274.8 n\Phi$; $C_{2B}/C_{20B} = 56.5$	SOD-323, SC-76	K•A
AH	ZMV930	ZETEX	var	V _R <12B; I _F <100мA; I _R <0.1 мкА; С _{25B} =4.35.5пФ	SOD-323, SC-76	K•A
A.J	ZMV931	ZETEX	var	V _R <12B; I _F <100мA; I _R <0.1 мкА; С _{25B} =6.57.8пФ	SOD-323, SC-76	K•A
AK	ZMV932	ZETEX	var	V _B <12B; I _F <100мA; I _B <0.1 мкА; С _{25B} =8.510.5 пФ	SOD-323, SC-76	K•A
AL	ZMV933	ZETEX	var	V _R <12 B; I _F <100 мА; I _R <0.1 мкА; С _{2.5 В} =1827 пФ	SOD-323, SC-76	K•A
AM	ZMV933A	ZETEX	var	V _R <12 B; I _F <100 мА; I _R <0.1 мкА; С _{2.5 В} =20.2524.75 пФ	SOD-323, SC-76	K•A
AN	ZMV934	ZETEX	var	V_R < 12 В; I_F < 100 мА; I_R < 0.1 мкА; $C_{2.5B}$ = 4065 пФ	SOD-323, SC-76	K◆A
AO	ZMV934A	ZETEX	var	V _R < 12 B; I _F < 100 мА; I _R < 0.1 мкА; С _{2.5 В} = 47.2557.75 пФ	SOD-323, SC-76	K•A
AP	CMDZ2L4	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 2.4 \text{B}; P_D < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
AR	CMDZ43L	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 43 \text{ B}; P_D \le 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
В	BAS16-03W	INF	di	$V_R < 80 \text{ B}; I_F < 250 \text{ mA}; V_F (I_F = 150 \text{ mA}) < 1.25 \text{ B}; I_R < 50 \text{ mKA}$	SOD-323, SC-76	K•A
В	BAT15098	SIEM	shd	$V_B < 4B$; $I_F < 110 \text{ mA}$; $V_F (I_F = 10 \text{ mA}) < 0.32B$; $C_D < 0.35 \text{ m}$	SOD-123	K•A





Код	Типономинал	Б	Φ	Особенности	Kopnyc	Ц:1•2
B0	BZX399C4V3	PHIL	dz	$V_Z(I_{ZT}=50 \text{ m/sA})=4.094.52 \text{ B}; P_D < 300 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
B1	BZX399C1V8	PHIL	dz	$V_Z(I_{ZT} = 50 \text{ mKA}) = 1.7151.89 \text{ B}; P_D \le 300 \text{ mB} \tau$	SOD-323, SC-76	K•A
B2	BZX399C2V0	PHIL	dz	$V_Z(I_{ZT}=50 \text{ mKA})=1.92.1 \text{ B; } P_D \le 300 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
B3	BZX399C2V2	PHIL	dz	$V_Z(I_{ZT}=50 \text{ mKA})=2.092.31 \text{ B}; P_D<300 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
B4	BZX399C2V4	PHIL	dz	V _Z (I _{ZT} = 50 mKA) = 2.282.52 B; P _D < 300 mBT	SOD-323, SC-76	K•A
B5	BZX399C2V7	PHIL	dz	$V_Z(I_{ZT} = 50 \text{ mKA}) = 2.572.84 \text{ B}; P_D < 300 \text{ mBT}$	SOD-323, SC-76	K•A
B6	BZX399C3V0	PHIL	dz	$V_Z(I_{ZT} = 50 \text{ m/sA}) = 2.853.15 \text{ B}; P_D < 300 \text{ mB} \text{T}$	SOD-323, SC-76	K • A
B7	BZX399C3V3	PHIL	dz	$V_2(I_{ZT}=50 \text{ mKA})=3.143.47 \text{ B}; P_0<300 \text{ mB}_T$	SOD-323, SC-76	K•A
B8	BZX399C3V6	PHIL	dz	$V_2(I_{ZT}=50 \text{ mKA})=3.423.78 \text{ B; } P_0 \le 300 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
B9	BZX399C3V9	PHIL	dz	$V_Z(I_{ZT}=50 \text{ mKA})=3.714.1 \text{ B}; P_D<300 \text{ mBT}$	SOD-323, SC-76	K ●A
BA	BZX399C4V7	PHIL	dz	$V_Z(I_{ZT}=50 \text{ mKA})=4.474.94 \text{ B; } P_D < 300 \text{ mBT}$	SOD-323, SC-76	K•A
BB	BZX399C5V1	PHIL	dz	$V_2(I_{ZT}=50 \text{ mKA}) = 4.855.36 \text{ B}; P_D < 300 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
BC	BZX399C5V6	PHIL	dz	$V_2(I_{ZI} = 50 \text{ mKA}) = 5.325.88 \text{ B; } P_0 < 300 \text{ mB} \text{ T}$	SOD-323, SC-76	K•A
BD	BZX399C6V2	PHIL	dz	$V_2(I_{77} = 50 \text{ mKA}) = 5.896.51 \text{ B}; P_0 < 300 \text{ mBT}$	SOD-323, SC-76	K•A
BD	ZHCS400	ZETEX	shd	$V_B < 40 \text{ B}; I_E < 400 \text{ mA}; V_E (I_E = 400 \text{ mA}) < 0.5 \text{ B}; I_B < 40 \text{ mKA}; C_D = 20 \text{ n} \Phi$	SOD-323, SC-76	K•A
BE	BZX399C6V8	PHIL	dz	$V_2(I_{ZT} = 50 \text{ mgA}) = 6.467.14 \text{ B; } P_D \le 300 \text{ mBT}$	SOD-323, SC-76	K•A
BF	BZX399C7V5	PHIL	dz	V ₂ (I _{2T} = 50 mKA) = 7.137.88 B; P _D < 300 mBT	SOD-323, SC-76	K•A
BG	BZX399C8V2	PHIL	dz	V _Z (I _{ZT} =50 mrA)=7.798.61B; P _D <300 mBT	SOD-323, SC-76	K•A
ВН	BZX399C9V1	PHIL	dz	V ₂ (I _{ZT} = 50 mrA) = 8.659.56B; P _D < 300 mBT	SOD-323, SC-76	K • A
BJ	BZX399C10	PHIL	dz	$V_2(I_{27} = 50 \text{ mgA}) = 9.510.5 \text{ B}; P_D < 300 \text{ mBT}$	SOD-323, SC-76	K•A
BK	BZX399C11	PHIL	dz	V ₂ (I ₂₁ = 50 mrA) = 10.4511.55 B; P _D < 300 mB	SOD-323, SC-76	K•A
BL	BZX399C12	PHIL	dz	V ₂ (I _{ZT} = 50 mrA) = 11.412.6B; P _D < 300 mBT	SOD-323, SC-76	K•A
BM	BZX399C13	PHIL	dz	V ₂ (I ₂₇ = 50 mrA) = 12.3513.65 B; P _D < 300 mB	SOD-323, SC-76	K•A
BN	BZX399C15	PHIL	dz	V ₂ (I _{2T} = 50 mKA) = 14.2515.75 B; P _D < 300 mB	SOD-323, SC-76	K•A
BP	BZX399C16	PHIL	dz	V ₂ (I ₂₇ = 50 mKA) = 15.216.8 B; P _D < 300 mB	SOD-323, SC-76	K•A
BP	CMDZ2L5	CSI	dz	$V_2(I_{2T} = 0.5 \text{ mA}) = 2.5 \text{ B; } P_D < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
BQ.	BZX399C18	PHIL	dz	V ₂ (I _{ZT} = 50 mKA) = 17.118.9B; P _D < 300 mB	SOD-323, SC-76	K•A
BR	BZX399C20	PHIL	dz	V ₂ (I ₂₇ =50 mKA)=1921B; P _D <300 mB	SOD-323, SC-76	K•A
BR	CMDZ47L	CSI	dz	V ₂ (I _{2T} = 0.5 mA) = 47 B; P _D < 250 mBT	SOD-323, SC-76	K•A
BS	BZX399C22	PHIL	dz	V ₂ (I ₂₇ =50 mKA)=20.923.1B; P ₀ <300 mB	SOD-323, SC-76	K•A
BT	BZX399C24	PHIL	dz	V ₂ (I ₂₇ =50 mKA) = 22.825.2B; P _D <300 MB	SOD-323, SC-76	K•A
BU	BZX399C27	PHIL	dz	V ₂ (I _{2T} =50 mKA) = 25.6528.35 B; P _D < 300 mB	SOD-323, SC-76	K•A
BV	BZX399C30	PHIL	dz	V ₂ (I ₂₇ =50 mKA) =28.531.5B; P _D <300 mB	SOD-323, SC-76	K•A
BW	BZX399C33	PHIL	dz	V ₂ (I ₂₇ =50 mKA)=31.3534.65 B; P _D <300 mB	SOD-323, SC-76	K•A
BX	BZX399C36	PHIL	dz	V ₂ (I _{2T} =50 mKA)=34.237.8B; P _D <300 mB	SOD-323, SC-76	K•A
BY	BZX399C39	PHIL	dz	V ₂ (I ₂₇ = 50 mkA) = 37.0540.95 B; P _D < 300 mB	SOD-323, SC-76	K•A
BZ	BZX399C43	PHIL	dz	V ₂ (I ₂₇ =50 mA)=40.8545.15 B; P _D <300 mB	SOD-323, SC-76	K•A
C	KV1832E	TOKO	var	С=417 пФ	SOD-323, SC-76	K•A
	BAT165	INF	shd	V _B <40 B; I _E <750 mA; V _E (I _E =750 mA)<0.7 B; C _D <12 πΦ	SOD-323, SC-76	K • A
	BAT65	SIEM	shd	$V_R < 30 \text{ B; } I_F < 500 \text{ mA; } V_F (I_F = 250 \text{ mA}) < 0.7 \text{ B; } I_R < 10 \text{ mKA; } C_D < 12 \text{ n}\Phi$	SOD-123	K•A
C1	1SS352	TOSH	di	V _R <80 B; I _F < 200 mA; V _F (I _F = 100 mA) < 1.2 B; I _R < 0.5 mkA	SOD-323, SC-76	K•A
C1	MMSZ5221BT1	ON	dz	V ₂ (I ₂₇ =20 mA)=2.282.52 B; I ₈ <100 mKA	SOD-323, 30-76	K•A
C2	MMSZ5222BT1	ON	dz	$V_2(I_{ZT}=20 \text{ mA})=2.262.32 \text{ B}, I_R < 100 \text{ mKA}$ $V_2(I_{ZT}=20 \text{ mA})=2.372.63 \text{ B}; I_R < 100 \text{ mKA}$	SOD-123	K•A
C3	MMSZ5222BT1	ON	dz	V ₂ (I _{2T} =20 mA)=2.572.63 B ₁ R ₁ 100 mKA V ₂ (I _{2T} =20 mA)=2.572.84 B ₁ R ₂ < 75 mKA	SOD-123	K•A
C4	MMSZ5224BT1	ON	dz	$V_2(I_{ZT} = 20 \text{ MA}) = 2.572.64 \text{ B}, I_R < 75 \text{ M/KA}$ $V_2(I_{ZT} = 20 \text{ MA}) = 2.662.94 \text{ B}; I_R < 75 \text{ M/KA}$	SOD-123	K•A
C48	CMHD4448	CNTRL	di	$V_2(I_{ZT} = 20 \text{ MA}) = 2.002.34 \text{ B}; I_R < 73 \text{ M/KA}$ $V_R < 75 \text{ B}; I_C < 500 \text{ MA}; V_C(I_C = 10 \text{ MA}) < 1 \text{ B}; C_D < 4\pi\Phi; t_{RR} < 4 \text{ HC}$	SOD-123	K•A
C5	MMSZ5225	VISH	dz	$V_2(I_{2T}=20 \text{ mA})=3 \text{ B}_1 I_R < 50 \text{ m/s}$	SOD-123	K•A
C5	MMSZ5225BT1	ON	dz	$V_Z(I_{ZT} = 20 \text{ MA}) = 3 \text{ B}; I_R \le 50 \text{ MKA}$ $V_Z(I_{ZT} = 20 \text{ MA}) = 2.853.15 \text{ B}; I_R \le 50 \text{ MKA}$	SOD-123 SOD-123	K•A
CA	MMSZ3223B11	VISH	dz	V _Z (I _{ZT} =20 MA)=2.853.15 B; I _R <50 MKA V _Z (I _{ZT} =50 MKA)=5.896.51 B; I _R <10 MKA	SOD-123	K•A
CA		ON	1000		100000000000000000000000000000000000000	K•A
(C3) (S)	MMSZ4691T1	200	dz	V _Z (I _{ZT} = 50 mKA) = 5.896.51 B; I _R < 10 mKA	SOD-123	100
CA	ZMV829B	ZETEX	var	$V_{B} < 25B$; $I_{F} < 200$ mA; $I_{B} < 0.02$ mKA; $C_{2B} = 7.798.61$ m Φ ; $C_{2B}/C_{20B} = 4.35.8$	SOD-323, SC-76	K•A
CB	ZMV830B	ZETEX	var	$V_R < 25B$; $I_F < 200$ MÅ; $I_R < 0.02$ MKÅ; $C_{2B} = 9.510.5$ n Φ ; $C_{2B}/C_{20B} = 4.56.0$	SOD-323, SC-76	K • A



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Код	Типономинал	Б	Ф	Особенности	Корпус	Ц:1•2
CC	MMSZ4678T1	ON	dz	$V_Z(I_{ZT} = 50 \text{ m/A}) = 1.711.89 \text{ B}; I_B < 7.5 \text{ m/A}$	SOD-123	K∙A
CC	ZMV831B	ZETEX	var	$V_B < 25B$; $I_F < 200 \text{ mA}$; $I_R < 0.02 \text{ mKA}$; $C_{2B} = 14.2515.75 \text{ n}\Phi$; $C_{2B}/C_{20B} = 4.56.0$	SOD-323, SC-76	K∙A
CC1	CMHZ5221B	CSI	dz	V _Z =2.4B(5%); P _D <500mB _T	SOD-123	K∙A
CC2	CMHZ5222B	CSI	dz	$V_Z = 2.5 B (5\%); P_D < 500 MBT$	SOD-123	K•A
CC3	CMHZ5223B	CSI	dz	V _Z =2.7B(5%); P _D <500mB _T	SOD-123	K•A
CC4	CMHZ5224B	CSI	dz	$V_Z = 2.8 B (5\%); P_D < 500 MBT$	SOD-123	K•A
CC5	CMHZ5225B	CSI	dz	$V_Z = 3.0 B (5\%); P_D < 500 MBT$	SOD-123	K•A
CD	MMSZ4679T1	ON	dz	V _Z (I _{ZT} = 50 mKA) = 1.902.10 B; I _R < 5 mKA	SOD-123	K∙A
CD	ZMV832B	ZETEX	var	$V_R < 25 \text{ B}; I_F < 200 \text{ mA}; I_R < 0.02 \text{ m/A}; C_{2B} = 20.923.1 \text{ n}\Phi; C_{2B}/C_{20B} = 56.5$	SOD-323, SC-76	K∙A
CD1	CMHZ5226B	CSI	dz	$V_Z = 3.3 B (5\%); P_D < 500 MBT$	SOD-123	K•A
CD2	CMHZ5227B	CSI	dz	$V_Z = 3.6 B (5\%); P_D < 500 MBT$	SOD-123	K∙A
CD3	CMHZ5228B	CSI	dz	V _Z =3.9B (5%); P _D <500 MB _T	SOD-123	K•A
CD4	CMHZ5229B	CSI	dz	$V_Z = 4.3 B (5\%), P_D < 500 MBT$	SOD-123	K•A
CD5	CMHZ5230B	CSI	dz	V _Z =4.7B(5%); P _D <500mB _T	SOD-123	K•A
CE	MMSZ4680T1	ON	dz	$V_Z(I_{ZT}=50 \text{ mKA})=2.092.31 \text{ B}; I_R < 4 \text{ mKA}$	SOD-123	K•A
CE	ZMV833B	ZETEX	var	V _B <25B; I _F <200 мА; I _B <0.02 мкА; С _{2B} = 31.3534.65 пФ; С _{2B} /С _{20B} = 56.5	SOD-323, SC-76	K◆A
CE1	CMHZ5231B	CSI	dz	V _Z =5.1B(5%); P _D <500mB _T	SOD-123	K•A
CE2	CMHZ5232B	CSI	dz	V _Z =5.6B(5%); P _D <500mBt	SOD-123	K∙A
CE3	CMHZ5233B	CSI	dz	V ₇ =6.0B(5%); P _D <500mBt	SOD-123	K•A
CE4	CMHZ5234B	CSI	dz	V _Z =6.2B(5%); P _D <500mBt	SOD-123	K•A
CE5	CMHZ5235B	CSI	dz	V _Z =6.8 B (5%); P _D <500 mB _T	SOD-123	K•A
CF	MMSZ4681	VISH	dz	$V_Z(I_{ZI} = 50 \text{ m/sA}) = 2.282.52 \text{ B}; I_B \le 2 \text{ m/sA}$	SOD-123	K•A
CF	MMSZ4681T1	ON	dz	$V_Z(I_{ZI} = 50 \text{ m/sA}) = 2.282.52 \text{ B}; I_B \le 2 \text{ m/sA}$	SOD-123	K•A
CF	ZMV834B	ZETEX	var	V _B <25B; I _F <200мA; I _B <0.02мкA; С _{2B} =44.6549.35пФ; С _{2B} /С _{20B} =56.5	SOD-323, SC-76	K∙A
CF1	CMHZ5236B	CSI	dz	V _Z =7.5B(5%); P _D <500mBT	SOD-123	K•A
CF2	CMHZ5237B	CSI	dz	V _Z =8.2B(5%); P _D <500 mBT	SOD-123	K•A
CF3	CMHZ5238B	CSI	dz	V _Z =8.7B(5%); P _D <500mBT	SOD-123	K•A
CF4	CMHZ5239B	CSI	dz	Vz = 9.1B (5%); Pp < 500 mBT	SOD-123	K•A
CF5	CMHZ5240B	CSI	dz	V _Z = 10 B (5%); P _D < 500 mB _T	SOD-123	K•A
CG	ZMV835B	ZETEX	var	$V_B < 25 B$; $I_F < 200 \text{ mA}$; $I_B < 0.02 \text{ mrA}$; $C_{2B} = 64.671.4 \text{ n}\Phi$; $C_{2B}/C_{20B} = 56.5$	SOD-323, SC-76	K•A
CH	MMSZ4682	VISH	dz	$V_Z(I_{ZI} = 50 \text{ mKA}) = 2.572.84 \text{ B}_1 \text{ I}_8 < 1 \text{ mKA}$	SOD-123	K∙A
CH	MMSZ4682T1	ON	dz	$V_7(I_{77} = 50 \text{ m/sA}) = 2.572.84 \text{ B}; I_8 < 1 \text{ m/sA}$	SOD-123	K∙A
CH1	CMHZ5241B	CSI	dz	V ₇ = 11 B (5%); P _D < 500 mBT	SOD-123	K•A
CH2	CMHZ5242B	CSI	dz	V _Z = 12 B (5%); P _D < 500 mBT	SOD-123	K•A
CH3	CMHZ5243B	CSI	dz	V ₂ = 13 B(5%); P _D < 500 mB _T	SOD-123	K•A
CH4	CMHZ5244B	CSI	dz	$V_Z = 14 B(5\%), P_D < 500 MBT$	SOD-123	K∙A
CH5	CMHZ5245B	CSI	dz	V _Z = 15 B(5%); P _D < 500 mBT	SOD-123	K•A
CJ	MMSZ4683	VISH	dz	$V_z(I_{zz} = 50 \text{ m/sA}) = 2.853.15 \text{ B}; I_B < 0.8 \text{ m/sA}$	SOD-123	K∙A
CJ	MMSZ4683T1	ON	dz	$V_Z(I_{ZT} = 50 \text{ m/sA}) = 2.853.15 \text{ B}; I_B < 0.8 \text{ m/sA}$	SOD-123	K◆A
CJ1	CMHZ5246B	CSI	dz	V _Z = 16 B (5%); P _D < 500 mBT	SOD-123	K•A
CJ2	CMHZ5247B	CSI	dz	Vz = 17B(5%); Pp < 500 mBT	SOD-123	K∙A
CJ3	CMHZ5248B	CSI	dz	V _Z = 18 B (5%); P _D < 500 mBT	SOD-123	K•A
CJ4	CMHZ5249B	CSI	dz	V _Z =19B(5%); P _D <500mBt	SOD-123	K•A
CJ5	CMHZ5250B	CSI	dz	V ₂ =20B(5%); P _D <500mBt	SOD-123	K•A
CK	MMSZ4684	VISH	dz	$V_Z(I_{ZT} = 50 \text{ mKA}) = 3.143.47 \text{ B}; I_R < 7.5 \text{ mKA}$	SOD-123	K∙A
CK	MMSZ4684T1	ON	dz	$V_Z(I_{ZT} = 50 \text{ mKA}) = 3.143.47 \text{ B}; I_B < 7.5 \text{ mKA}$	SOD-123	K•A
CK1	CMHZ5251B	CSI	dz	V _Z =22B(5%); P _D <500mBT	SOD-123	K◆A
CK2	CMHZ5252B	CSI	dz	V _Z =24B(5%); P _D <500mBT	SOD-123	K•A
CK3	CMHZ5253B	CSI	dz	V _Z = 25 B (5%); P _D < 500 mB _T	SOD-123	K•A
CK4	CMHZ5254B	CSI	dz	V _Z =27B(5%); P _D <500 mBT	SOD-123	K•A
CK5	CMHZ5255B	CSI	dz	V _Z = 28 B (5%); P _D < 500 mBT	SOD-123	K•A
CL1	MMSZ2V4ET1	ON	dz	V _Z (I _{ZT} = 5 MA) = 2.282.52B; I _B < 50 MKA	SOD-123	K•A

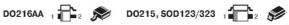




Код	Типономинал	Б	Φ	Особенности	Корпус	Ц:1•2
CL2	MMSZ2V7ET1	ON	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 2.572.84 \text{ B}; I_R < 20 \text{ m/sA}$	SOD-123	K•A
CL3	MMSZ3V0ET1	ON	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 2.853.15 \text{ B}; I_B < 10 \text{ m/sA}$	SOD-123	K∙A
CL4	MMSZ3V3ET1	ON	dz	V _Z (I _{ZT} = 5 mA) = 3.143.47 B; I _B < 5 mrA	SOD-123	K•A
CL5	MMSZ3V6ET1	ON	dz	V _Z (I _{ZT} = 5 mA) = 3.423.78 B; I _B < 5 mKA	SOD-123	K∙A
CL6	MMSZ3V9ET1	ON	dz	V _Z (I _{ZT} = 5 mA) = 3.714.10 B; I _B < 3 mrA	SOD-123	K∙A
CL7	MMSZ4V3ET1	ON	dz	$V_2(I_{77} = 5 \text{ mA}) = 4.094.52 \text{ B}; I_{8} < 3 \text{ m/sA}$	SOD-123	K∙A
CL8	MMSZ4V7ET1	ON	dz	$V_2(I_{21} = 5 \text{ mA}) = 4.474.94 \text{ B; } I_{8} < 2 \text{ mKA}$	SOD-123	K∙A
CL9	MMSZ5V1ET1	ON	dz	V ₂ (I _{2T} = 5 mA) = 4.855.36 B; I _B < 1 mrA	SOD-123	K∙A
CM	MMSZ4685	VISH	dz	$V_2(I_{TT} = 50 \text{ mKA}) = 3.423.78 \text{ B}; I_B < 7.5 \text{ mKA}$	SOD-123	K∙A
CM	MMSZ4685T1	ON	dz	$V_2(I_{77} = 50 \text{ mKA}) = 3.423.78 \text{ B}; I_8 < 7.5 \text{ mKA}$	SOD-123	K•A
CM1	CMHZ5256B	CSI	dz	V _z = 30 B (5%); P _D < 500 мВт	SOD-123	K•A
CM1	MMSZ5V6ET1	ON	dz	V ₂ (I ₂₁ = 5 mA) = 5.325.88 B; I ₈ < 3 mKA	SOD-123	K•A
CM2	CMHZ5257B	CSI	dz	V _Z =33B(5%); P _D <500mBT	SOD-123	K•A
CM2	MMSZ6V2ET1	ON	dz	V ₂ (I _{2T} =5 mA) = 5.896.51 B; I _B < 2 mKA	SOD-123	K•A
CM3	CMHZ5258B	CSI	dz	V _Z = 36 B (5%); P _D < 500 mB _T	SOD-123	K•A
CM3	MMSZ6V8ET1	ON	dz	V ₂ (I _{2T} = 5 mA) = 6.467.14 B; I _B < 1 mrA	SOD-123	K•A
CM4	CMHZ5259B	CSI	dz	V _Z =39B(5%); P _D <500mBT	SOD-123	K•A
CM4	MMSZ7V5ET1	ON	dz	V ₂ (I ₂₇ =5 MA)=7.137.88 B; I ₈ <0.7 MKA	SOD-123	K•A
CM5	CMHZ5260B	CSI	dz	V ₇ =43B(5%); P _D <500 MBT	SOD-123	K•A
CM5	MMSZ8V2ET1	ON	dz	V ₂ (I ₂₇ =5 MA) = 7.798.61 B; I ₈ <0.5 MKA	SOD-123	K•A
CM6	MMSZ9V1ET1	ON	dz	V ₂ (I _{2T} = 5 mA) = 8.65 9.56 B; I _R < 0.2 mkA	SOD-123	K•A
CM7	MMSZ10ET1	ON	dz	$V_2(I_{ZT}=5 \text{ MA})=0.039.30 \text{ B}, I_{B}<0.2 \text{ MKA}$ $V_2(I_{ZT}=5 \text{ MA})=9.510.5 \text{ B}; I_{B}<0.1 \text{ MKA}$	SOD-123	K•A
CM8		ON	_	$V_2(I_{ZT}=5 \text{ MA})=9.510.56$, $I_8 \times 0.1 \text{ MKA}$	SOD-123	K•A
CM9	MMSZ11ET1	ON	dz			K•A
CN	MMSZ12ET1	VISH	dz	V _Z (I _{ZT} =5 mA) = 11.412.6 B; I _R <0.1 mrA	SOD-123	K•A
(701.02	MMSZ4686	100000	dz	V _Z (I _{ZT} = 50 mKA) = 3.714.10B; I _R < 5 mKA	SOD-123	K•A
CN	MMSZ4686T1	ON	dz	V _Z (I _{ZT} =50 mKA) = 3.714.10B; I _B < 5 mKA	SOD-123	2.5
CN1	CMHZ5261B	CSI	dz	V _Z =47B(5%); P _D <500MBT	SOD-123	K•A
CN1	MMSZ13ET1	ON	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 12.3513.65 \text{ B}; I_R < 0.05 \text{ mkA}$	SOD-123	K•A
CN2	CMHZ5262B	CSI	dz	V _Z =51 B (5%); P _D <500 mB _T	SOD-123	K•A
CN2	MMSZ15ET1	ON	dz	V _Z (I _{ZT} = 5 mA) = 14.2515.75 B; I _R < 0.05 mrA	SOD-123	K•A
CN3	CMHZ5263B	CSI	dz	V _Z =56B(5%); P _D <500mB _T	SOD-123	K•A
CN3	MMSZ16ET1	ON	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 15.216.8 \text{ B}; I_R < 0.05 \text{ mKA}$	SOD-123	K•A
CN4	CMHZ5264B	CSI	dz	V _Z =60 B (5%); P _D <500 mBT	SOD-123	K•A
CN4	MMSZ18ET1	ON	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 17.118.9 \text{ B}; I_R < 0.05 \text{ mKA}$	SOD-123	K∙A
CN5	CMHZ5265B	CSI	dz	V ₂ =62B(5%); P _D <500mB _T	SOD-123	K∙A
CN5	MMSZ20ET1	ON	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 19.021.0 \text{ B}; I_R < 0.05 \text{ mKA}$	SOD-123	K∙A
CN6	MMSZ22ET1	ON	dz	$V_Z(I_{ZT}=5 \text{ mA}) = 20.923.1 \text{ B; } I_{Pl} < 0.05 \text{ mKA}$	SOD-123	K•A
CN7	MMSZ24ET1	ON	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 22.825.2 \text{ B; } I_{B} < 0.05 \text{ mKA}$	SOD-123	K•A
CN8	MMSZ27ET1	ON	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 25.6528.35 \text{ B}; I_R < 0.05 \text{ mkA}$	SOD-123	K•A
CN9	MMSZ30ET1	ON	dz	$V_2(I_{ZT} = 5 \text{ mA}) = 28.5031.5 \text{ B}; I_R < 0.05 \text{ m/sA}$	SOD-123	K∙A
CO3	CMHD2003	CNTRL	di	V_R <250 B; I_F <250 mA; V_F (I_F =100 mA)<1B; C_D =1.5 n Φ ; t_{RR} <50 Hc	SOD-123	K∙A
CP	CMDZ2L7	CSI	dz	$V_2(I_{ZT} = 0.5 \text{ mA}) = 2.7 \text{ B}; P_0 < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K∙A
CP	MMSZ4687	VISH	dz	$V_Z(I_{ZT} = 50 \text{ mKA}) = 4.094.52 \text{ B}; I_R < 4 \text{ mKA}$	SOD-123	K•A
CP	MMSZ4687T1	ON	dz	$V_Z(I_{ZT} = 50 \text{ mKA}) = 4.094.52 \text{ B}; I_R < 4 \text{ mKA}$	SOD-123	K•A
CP1	CMHZ5266B	CSI	dz	$V_2 = 68 B(5\%); P_0 < 500 MBT$	SOD-123	K∙A
CP1	MMSZ33ET1	ON	dz	$V_2(I_{ZT}=5 \text{ mA}) = 31.3534.65 \text{ B}; I_B < 0.05 \text{ m/sA}$	SOD-123	K∙A
CP2	CMHZ5267B	CSI	dz	V _z = 75 B (5%); P _D < 500 mBT	SOD-123	K∙A
CP2	MMSZ36ET1	ON	dz	V _Z (I _{ZT} = 5 mA) = 34.237.8 B; I _B < 0.05 mrA	SOD-123	K•A
CP3	CMHZ5268B	CSI	dz	$V_2 = 82 B(5\%); P_0 < 500 MBT$	SOD-123	K•A
CP3	MMSZ39ET1	ON	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 37.0541.0 \text{ B}; I_B < 0.05 \text{ mkA}$	SOD-123	K∙A
CP4	CMHZ5269B	CSI	dz	V ₂ =87B(5%); P ₀ <500mBT	SOD-123	K•A









Код	Типономинал	6	Ф	Особенности	Корпус	Ц:1•2
CP5	CMHZ5270B	CSI	dz	V _Z =91 B(5%); P _D <500 mBT	SOD-123	K∙A
CP5	MMSZ47ET1	ON	dz	V _Z (I _{ZT} =5 mA) =44.6549.35 B; I _R <0.05 mкA	SOD-123	K•A
CP6	MMSZ51ET1	ON	dz	$V_Z(I_{ZT}=5 \text{ mA}) = 48.4553.55 \text{ B; }I_R \le 0.05 \text{ mKA}$	SOD-123	K∙A
CP7	MMSZ56ET1	ON	dz	V _Z (I _{ZT} =5 mA) =53.2058.80 B; I _R <0.05 mkA	SOD-123	K∙A
CR1	CMHZ5271B	CSI	dz	Vz = 100 B (5%); Po < 500 mBT	SOD-123	K∙A
CR2	CMHZ5272B	CSI	dz	V _Z = 110 B (5%); P _D < 500 mBT	SOD-123	K•A
CR3	CMHZ5273B	CSI	dz	V _Z =120 B (5%); P _D <500 mBT	SOD-123	K◆A
CR4	CMHZ5274B	CSI	dz	Vz=130B(5%); Po<500 mBT	SOD-123	K•A
CR5	CMHZ5275B	CSI	dz	Vz=140 B(5%); Po<500 mBT	SOD-123	K∙A
CS1	CMHZ5276B	CSI	dz	V _Z =150 B (5%); P _D <500 mB _T	SOD-123	K∙A
CS2	CMHZ5277B	CSI	dz	V _Z =160 B (5%); P _D <500 mBT	SOD-123	K◆A
CS3	CMHZ5278B	CSI	dz	$V_Z = 170 \text{ B} (5\%); P_D < 500 \text{ mB} \text{T}$	SOD-123	K•A
CS4	CMHZ5279B	CSI	dz	V _Z = 180 B (5%); P _D < 500 mB _T	SOD-123	K•A
CS5	CMHZ5280B	CSI	dz	$V_Z = 190 \text{ B} (5\%); P_D < 500 \text{ mB} \text{T}$	SOD-123	K∙A
CT	MMSZ4688	VISH	dz	$V_Z(I_{ZT} = 50 \text{ m/A}) = 4.474.94 \text{ B}; I_R < 10 \text{ m/A}$	SOD-123	K•A
CT	MMSZ4688T1	ON	dz	$V_Z(I_{ZT} = 50 \text{ mKA}) = 4.474.94 \text{ B}; I_8 < 10 \text{ mKA}$	SOD-123	K◆A
CT1	CMHZ5281B	CSI	dz	Vz=200B(5%); Po<500mBT	SOD-123	K•A
CU	MMSZ4689	VISH	dz	$V_Z(I_{Z1} = 50 \text{ m/sA}) = 4.855.36 \text{ B}; I_R < 10 \text{ m/sA}$	SOD-123	K∙A
CU	MMSZ4689T1	ON	dz	$V_z(I_{z1} = 50 \text{ m/A}) = 4.855.36 \text{ B}; I_B < 10 \text{ m/A}$	SOD-123	K∙A
CV	MMSZ4690	VISH	dz	$V_Z(I_{Z1} = 50 \text{ m/sA}) = 5.325.88 \text{ B}; I_8 < 10 \text{ m/sA}$	SOD-123	K∙A
CV	MMSZ4690T1	ON	dz	$V_Z(I_{ZT}=50 \text{ mKA})=5.325.88 \text{ B}; I_R < 10 \text{ mKA}$	SOD-123	K•A
CX	MMSZ4692	VISH	dz	$V_Z(I_{ZT} = 50 \text{ m/sA}) = 6.467.14 \text{ B}; I_B < 10 \text{ m/sA}$	SOD-123	K∙A
CX	MMSZ4692T1	ON	dz	$V_Z(I_{ZT} = 50 \text{ m/sA}) = 6.467.14 \text{ B}; I_B < 10 \text{ m/sA}$	SOD-123	K∙A
CY	MMSZ4693	VISH	dz	$V_Z(I_{ZT}=50 \text{ mKA})=7.137.88 \text{ B}; I_8 < 10 \text{ mKA}$	SOD-123	K∙A
CY	MMSZ4693T1	ON	dz	$V_{z}(I_{z1}=50 \text{ mrA})=7.137.88 \text{ B}; I_{B} < 10 \text{ mrA}$	SOD-123	K•A
CZ	MMSZ4694	VISH	dz	$V_Z(I_{ZI}=50 \text{ mKA})=7.798.61 \text{ B}; I_8 \le 1 \text{ mKA}$	SOD-123	K•A
CZ	MMSZ4694T1	ON	dz	$V_Z(I_{ZT} = 50 \text{ m/sA}) = 7.798.61 \text{ B}; I_R < 1 \text{ m/sA}$	SOD-123	K∙A
D	1SS376	ROHM	di	$V_R < 250 \text{ B}; I_F < 300 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 1.2 \text{ B}; t_{PR} < 100 \text{ HC}$	SOD-323, SC-76	K∙A
D	BAS21-03W	INF	di	$V_B \le 200 \text{ B}; I_F \le 250 \text{ mA}; V_F (I_F = 100 \text{ mA}) \le 1.0 \text{ B}; I_R \le 0.1 \text{ mKA}$	SOD-323, SC-76	K•A
D1	MMSZ5226	VISH	dz	$V_Z(I_{Z1} = 20 \text{ mA}) = 3.3 \text{ B}; I_8 \le 25 \text{ mKA}$	SOD-123	K•A
D1	MMSZ5226BT1	ON	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 3.143.47 \text{ B; } I_R \le 25 \text{ m/KA}$	SOD-123	K∙A
D2	MMSZ5227	VISH	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 3.6 \text{ B}; I_B < 15 \text{ m/s}$	SOD-123	K∙A
D2	MMSZ5227BT1	ON	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 3.423.78 \text{ B}; I_R < 15 \text{ mKA}$	SOD-123	K◆A
DG	MMSZ5228	VISH	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 3.9 \text{ B}; I_R < 10 \text{ mKA}$	SOD-123	K◆A
DG .	MMSZ5228BT1	ON	dz	V _Z (I _{ZT} =20 mA)=3.714.10 B; I _R <10 mKA	SOD-123	K∙A
D4	MMSZ5229	VISH	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 4.3 \text{ B}; I_R < 5 \text{ m/KA}$	SOD-123	K∙A
D4	MMSZ5229BT1	ON	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 4.094.52 \text{ B; } I_B \le 5 \text{ m/KA}$	SOD-123	K∙A
D5	MMSZ5230	VISH	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 4.7 \text{ B}; I_R < 5 \text{ mKA}$	SOD-123	K•A
D5	MMSZ5230BT1	ON	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 4.474.94 \text{ B}; I_B < 5 \text{ m/A}$	SOD-123	K◆A
D76	BAR18J	SGS	shd	$V_{BR} > 70B$; $V_F (I_F = 1 \text{ mA}) < 0.41 \text{ B}$; $I_R < 200 \text{ hA}$; $C_T < 1.7 \text{ n}$	SOD-323, SC-76	K∙A
DA	MMSZ4708	VISH	dz	$V_Z(I_{ZT} = 50 \text{ m/sA}) = 20.923.1 \text{ B}; I_R < 0.01 \text{ m/sA}$	SOD-123	K∙A
DA	MMSZ4708T1	ON	dz	$V_Z(I_{ZT} = 50 \text{ m/KA}) = 20.923.1 \text{ B; } I_R < 0.01 \text{ m/KA}$	SOD-123	K∙A
DC	MMSZ4695	VISH	dz	$V_Z(I_{ZT} = 50 \text{ m/sA}) = 8.279.14 \text{ B}; I_R < 1 \text{ m/sA}$	SOD-123	K∙A
DC	MMSZ4695T1	ON	dz	$V_Z(I_{ZT} = 50 \text{ m/sA}) = 8.279.14 \text{ B}; I_R < 1 \text{ m/sA}$	SOD-123	K•A
DD	MMSZ4696	VISH	dz	$V_Z(I_{ZT} = 50 \text{ m/A}) = 8.659.56 \text{ B}; I_B < 1 \text{ m/A}$	SOD-123	K∙A
DD	MMSZ4696T1	ON	dz	$V_Z(I_{ZT} = 50 \text{ m/A}) = 8.659.56 \text{ B}; I_R < 1 \text{ m/A}$	SOD-123	K∙A
DE	MMSZ4697	VISH	dz	$V_Z(I_{ZT} = 50 \text{ mKA}) = 9.510.5 \text{ B}; I_R \le 1 \text{ mKA}$	SOD-123	K∙A
DE	MMSZ4697T1	ON	dz	$V_Z(I_{ZT} = 50 \text{ m/A}) = 9.510.5 \text{ B}; I_R \le 1 \text{ m/A}$	SOD-123	K∙A
DF	MMSZ4698	VISH	dz	$V_Z(I_{ZT} = 50 \text{ m/sA}) = 10.511.6 \text{ B}; I_R < 0.05 \text{ m/sA}$	SOD-123	K∙A
DF	MMSZ4698T1	ON	dz	$V_Z(I_{Z1} = 50 \text{ mKA}) = 10.511.6 \text{ B}; I_R < 0.05 \text{ mKA}$	SOD-123	K•A
DH	MMSZ4699	VISH	dz	$V_Z(I_{ZT} = 50 \text{ mKA}) = 11.412.6 \text{ B}; I_R < 0.05 \text{ mKA}$	SOD-123	K∙A
DH	MMSZ4699T1	ON	dz	$V_Z(I_{ZT} = 50 \text{ m/sA}) = 11.412.6 \text{ B}; I_B < 0.05 \text{ m/sA}$	SOD-123	K∙A





Код	Типономинал	Б	Ф	Особенности Корг	пус Ц:1•2
DJ	MMSZ4700	VISH	dz	$V_2(I_{2T} = 50 \text{ mKA}) = 12.413.7 \text{ B}; I_B < 0.05 \text{ mKA}$ SOD-123	K∙A
DJ	MMSZ4700T1	ON	dz	$V_2(I_{21} = 50 \text{ mKA}) = 12.413.7 \text{ B}; I_8 < 0.05 \text{ mKA}$ SOD-123	K∙A
DK	MMSZ4701	VISH	dz	$V_2(I_{2T} = 50 \text{ m/sA}) = 13.314.7 \text{ B}; I_{B} < 0.05 \text{ m/sA}$ SOD-123	K∙A
DK	MMSZ4701T1	ON	dz	$V_2(I_{ZT} = 50 \text{ m/sA}) = 13.314.7 \text{ B}; I_8 < 0.05 \text{ m/sA}$ SOD-123	K∙A
DM	MMSZ4702	VISH	dz	$V_Z(I_{ZT} = 50 \text{ mKA}) = 14.315.8 \text{ B}; I_B < 0.05 \text{ mKA}$ SOD-123	K∙A
DM	MMSZ4702T1	ON	dz	$V_2(I_{ZT} = 50 \text{ m/A}) = 14.315.8 \text{ B}; I_B < 0.05 \text{ m/A}$ SOD-123	K∙A
DN	MMSZ4703	VISH	dz	$V_2(I_{ZT} = 50 \text{ m/sA}) = 15.216.8 \text{ B}; I_B < 0.05 \text{ m/sA}$ SOD-123	K∙A
DN	MMSZ4703T1	ON	dz	$V_2(I_{2T} = 50 \text{ m/sA}) = 15.216.8 \text{ B}; I_8 < 0.05 \text{ m/sA}$ SOD-123	K∙A
DP	CMDZ2L8	CSI	dz	$V_2(I_{ZT} = 0.5 \text{ mA}) = 2.8 \text{B}; P_0 < 250 \text{ mB} \text{T}$ SOD-323,	SC-76 K • A
DP	MMSZ4704	VISH	dz	$V_2(I_{ZT} = 50 \text{ mKA}) = 16.217.9B; I_B < 0.05 \text{ mKA}$ SOD-123	K∙A
DP	MMSZ4704T1	ON	dz	$V_2(I_{ZT} = 50 \text{ mKA}) = 16.217.9B; I_B < 0.05 \text{ mKA}$ SOD-123	K∙A
DT	MMSZ4705	VISH	dz	$V_2(I_{2T} = 50 \text{ mKA}) = 17.118.9 \text{ B}; I_8 < 0.05 \text{ mKA}$ SOD-123	K∙A
DT	MMSZ4705T1	ON	dz	$V_2(I_{27} = 50 \text{ m/sA}) = 17.118.9 \text{ B}; I_0 < 0.05 \text{ m/sA}$ SOD-123	K∙A
DU	MMSZ4706	VISH	dz	$V_2(I_{TT} = 50 \text{ m/KA}) = 18.120.0 \text{ B}; I_B < 0.05 \text{ m/KA}$ SOD-123	K•A
DU	MMSZ4706T1	ON	dz	$V_2(I_{2T} = 50 \text{ m/sA}) = 18.120.0 \text{ B}; I_B < 0.05 \text{ m/sA}$ SOD-123	K•A
DV	MMSZ4707	VISH	dz	$V_2(I_{27} = 50 \text{ mKA}) = 19.021.0 \text{ B}; I_B < 0.01 \text{ mKA}$ SOD-123	K•A
DV	MMSZ4707T1	ON	dz	$V_2(I_{27} = 50 \text{ mKA}) = 19.021.0 \text{ B; } I_8 < 0.01 \text{ mKA}$ SOD-123	K∙A
DY	MMSZ4710	VISH	dz	$V_2(I_{27}=50 \text{ mKA}) = 23.826.3 \text{ B}; I_B < 0.01 \text{ mKA}$ SOD-123	K∙A
DY	MMSZ4710T1	ON	dz	$V_2(I_{77} = 50 \text{ m/A}) = 23.826.3 \text{ B}; I_{8} < 0.01 \text{ m/A}$ SOD-123	K∙A
DZ	MMSZ4709	VISH	dz	V ₂ (I ₂₇ =50 mKA) = 22.825.2 B; I _B < 0.01 mKA SOD-123	K∙A
DZ	MMSZ4709T1	ON	dz	V ₂ (I _{2T} = 50 mKA) = 22.825.2B; I _B < 0.01 mKA SOD-123	K∙A
E	1SS380	ROHM	di	V _B <40 B; I _E < 225 mA; V _E (I _E = 100 mA) < 1.2 B; I _B < 0.01 mkA SOD-323,	1005 60
E1	MMSZ5231	VISH	dz	V ₂ (I _{2T} =20 mA)=5.1B; I ₈ <5 mKA SOD-123	K•A
E1	MMSZ5231BT1	ON	dz	V ₂ (I ₂₁ = 20 mA) = 4.855.36 B; I ₈ < 5 mkA SOD-123	K∙A
E2	MMSZ5232	VISH	dz	V _z (I _{zz} = 20 mA) = 5.6 B; I _B < 5 mkA SOD-123	K∙A
E2	MMSZ5232BT1	ON	dz	V ₂ (I ₂₇ = 20 mA) = 5.32 5.88 B; I ₈ < 5 mkA SOD-123	K∙A
E3	MMSZ5233	VISH	dz	$V_2(I_{71}=20 \text{ mA})=6.0 \text{ B; } I_{8}<5 \text{ m/sA}$ SOD-123	K∙A
E3	MMSZ5233BT1	ON	dz	V ₂ (I _{2T} =20 mA)=5.706.30 B; I _B <5 mkA SOD-123	K∙A
E4	MMSZ5234	VISH	dz	$V_2(I_{27} = 20 \text{ mA}) = 6.2 \text{ B}; I_8 \le 5 \text{ mKA}$ SOD-123	K∙A
E4		ON	dz	V ₂ (I ₂₁ = 20 mA) = 5.896.51 B; I ₈ < 5 mkA SOD-123	K∙A
E5	MMSZ5235	VISH	dz	V ₂ (I ₂₁ = 20 mA) = 6.8 B; I ₈ < 3 mkA SOD-123	K∙A
E5		ON	dz	V ₂ (I _{2T} =20 mA)=6.467.14 B; I _B <3 mкA SOD-123	K∙A
EA	MMSZ4711	VISH	dz	V ₂ (I ₂₇ =50 mKA) = 25.728.4 B; I _B < 0.01 mKA SOD-123	K∙A
EA	MMSZ4711T1	ON	dz	V _Z (I _{ZT} = 50 mKA) = 25.728.4 B; I _B < 0.01 mKA SOD-123	K∙A
EC	MMSZ4712	VISH	dz	V ₂ (I _{2T} = 50 mKA) = 26.629.4 B ₁ I ₈ < 0.01 mKA SOD-123	K∙A
EC	MMSZ4712T1	ON	dz	V ₂ (I ₂₇ = 50 mKA) = 26.629.4 B, I _B < 0.01 mKA SOD-123	K∙A
ED	MMSZ4713	VISH	dz	V ₂ (I ₂₇ =50 mKA) = 28.531.5B; I ₂ < 0.01 mKA SOD-123	K∙A
ED	MMSZ4713T1	ON	dz	V _Z (I _{ZI} = 50 mKA) = 28.531.5B; I _B < 0.01 mKA SOD-123	K∙A
EE	MMSZ4714	VISH	dz	V _Z (I _{ZZ} = 50 mKA) = 31.434.7B; I _R < 0.01 mKA SOD-123	K∙A
EE	MMSZ4714T1	ON	dz	V ₂ (I _{ZI} = 50 mKA) = 31.434.7B; I _B < 0.01 mKA SOD-123	K•A
EF	MMSZ4715	VISH	dz	V ₂ (I ₂₇ =50 mKA) = 34.2 37.8 B; I ₂ < 0.01 mKA SOD-123	K∙A
EF	MMSZ4715T1	ON	dz	V ₂ (I ₂₇ =50 mKA) =34.237.8 B; I ₈ <0.01 mKA SOD-123	K∙A
EH	MMSZ4716	VISH	dz	V ₂ (I ₂₇ =50 mKA)=37.141.0B; I _B <0.01 mKA SOD-123	K•A
EH	MMSZ4716T1	ON	dz	V ₂ (I ₂₇ = 50 mKA) = 37.0540.95 B; I ₈ < 0.01 mKA SOD-123	K•A
EJ	MMSZ4717	VISH	dz	V ₂ (I _{2T} = 50 mrA) = 40.945.2B; I ₈ < 0.01 mrA SOD-123	K∙A
EJ	MMSZ4717T1	ON	dz	V ₂ (I _{2T} = 50 mrA) = 40.8545.15 B; I _B < 0.01 mrA SOD-123	K∙A
F	KV1831E	TOKO	var	C=2.522nΦ SOD-323,	
F1	MMSZ5236	VISH	dz	$V_z(I_{zz} = 20 \text{ mA}) = 7.5 \text{ B}; I_B < 5 \text{ mKA}$ SOD-123	K∙A
F1	MMSZ5236BT1	ON	dz	$V_2(I_{2T} = 20 \text{ mA}) = 7.137.88 \text{ B; } I_B \le 3 \text{ m/sA}$ SOD-123	K∙A
F2	MMSZ5237	VISH	dz	$V_2(I_{21}=20 \text{ mA})=8.2 \text{ B; } I_9 < 5 \text{ m/A}$ SOD-123	K∙A
F2	MMSZ5237BT1	ON	dz	V ₂ (I _{2T} =20 mA)=7.798.61B; I _B <3 mkA SOD-123	K∙A
	1	1	1	$V_Z(I_{ZI} = 20 \text{ mA}) = 8.7 \text{ B}; I_B < 5 \text{ m/A}$ SOD-123	K∙A





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Код	Типономинал	Б	Ф	Особенности	Корпус	Ц:1•2
F3	MMSZ5238BT1	ON	dz	$V_Z(I_{ZT}=20 \text{ mA})=8.279.14 \text{ B; }I_R \le 3 \text{ mKA}$	SOD-123	K∙A
F4	MMSZ5239	VISH	dz	$V_Z(I_{Z1} = 20 \text{ mA}) = 9.1 \text{ B; } I_B < 5 \text{ m/cA}$	SOD-123	K•A
F4	MMSZ5239BT1	ON	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 8.659.56 \text{ B}; I_R < 3 \text{ mKA}$	SOD-123	K•A
F5	1SS403	TOSH	di	V_R < 200 B; I_F < 300 mA; V_F (I_F = 100 mA) < 1.2 B; I_R < 1 mkA; t_{RR} < 60 HC	SOD-323, SC-76	K•A
F5	MMSZ5240	VISH	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 10 \text{ B}; I_R < 3 \text{ mkA}$	SOD-123	K•A
F5	MMSZ5240BT1	ON	dz	$V_Z(I_{ZT}=20 \text{ mA})=9.510.5 \text{B}; I_R < 3 \text{ mkA}$	SOD-123	K•A
FP	CMDZ3L3	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 3.3 \text{ B}; P_D < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K • A
G	BAR63-03W	INF	pin	$V_R < 50 \text{ B}; I_F < 100 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 1.2 \text{ B}; I_R < 0.01 \text{ mKA}$	SOD-323, SC-76	K•A
G	KV1181E	TOKO	var	С=216 nФ	SOD-323, SC-76	K∙A
GP	CMDZ3L6	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 3.6 \text{B}; P_D < 250 \text{ mBT}$	SOD-323, SC-76	K•A
Н	BBY51-03W	INF	var	$V_R < 7B$; $I_F < 20$ mA; $I_R < 0.01$ mrA; $C_{1B} = 5.055.75$ n Φ ; $C4V = 2.53.7$ n Φ	SOD-323, SC-76	K∙A
H1	MMSZ5241	VISH	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 11 \text{ B}; I_R < 3 \text{ mkA}$	SOD-123	K•A
H1	MMSZ5241BT1	ON	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 10.4511.55 \text{ B}; I_R < 2 \text{ mkA}$	SOD-123	K•A
H2	MMSZ5242	VISH	dz	$V_Z(I_{Z1} = 20 \text{ mA}) = 12 \text{ B}; I_R \le 3 \text{ mKA}$	SOD-123	K•A
H2	MMSZ5242BT1	ON	dz	$V_Z(I_{ZT} = 20 \text{ mA}) = 11.412.6 \text{ B}; I_R < 1 \text{ m/sA}$	SOD-123	K•A
H 3	MMSZ5243	VISH	dz	$V_Z(I_{ZT} = 9.5 \text{ mA}) = 13 \text{ B}; I_B < 0.5 \text{ mKA}$	SOD-123	K•A
H 3	MMSZ5243BT1	ON	dz	V _Z (I _{ZT} = 9.5 mA) = 12.3513.65 B; I _R < 0.5 mrA	SOD-123	K•A
H 4	MMSZ5244	VISH	dz	$V_Z(I_{Z1} = 8.5 \text{ mA}) = 14 \text{ B; } I_B < 0.1 \text{ m/sA}$	SOD-123	K∙A
H 4	MMSZ5244BT1	ON	dz	V _Z (I _{ZT} = 8.5 mA) = 13.3014.70 B; I _R < 0.1 mkA	SOD-123	K•A
H5	MMSZ5245	VISH	dz	$V_z(I_{zz} = 8.5 \text{ mA}) = 15 \text{B}; I_R < 0.1 \text{ mKA}$	SOD-123	K ∙ A
H5	MMSZ5245BT1	ON	dz	$V_Z(I_{ZT} = 8.5 \text{ mA}) = 14.2515.75 \text{ B; } I_B < 0.1 \text{ m/sA}$	SOD-123	K•A
HP	CMDZ3L9	CSI	dz	$V_Z(I_{ZT}=0.5 \text{ mA}) = 3.9 \text{B}; P_0 < 250 \text{ mB}T$	SOD-323, SC-76	K∙A
I (бел)	BBY52-03W	INF	var	$V_B < 7B$; $I_E < 20$ mA; $I_B < 0.01$ mKA; $C_{1B} = 1.42.2$ n Φ ; $C_{4B} = 0.851.45$ n Φ	SOD-323, SC-76	K•A
J1	MMSZ5246	VISH	dz	$V_2(I_{21} = 7.8 \text{ mA}) = 16 \text{ B}; I_B < 0.1 \text{ m/sA}$	SOD-123	K•A
J1	MMSZ5246BT1	ON	dz	$V_z(I_{z1} = 7.8 \text{ mA}) = 15.216.8 \text{ B}; I_B < 0.1 \text{ mKA}$	SOD-123	K•A
J2	MMSZ5247	VISH	dz	$V_2(I_{ZI} = 7.4 \text{ mA}) = 17B; I_B < 0.1 \text{ mkA}$	SOD-123	K•A
J2	MMSZ5247BT1	ON	dz	V ₂ (I ₂₇ =7.0 mA) = 16.1517.85 B; I _B < 0.1 mrA	SOD-123	K•A
J3	MMSZ5248	VISH	dz	$V_Z(I_{ZT} = 7.0 \text{ mA}) = 18 \text{ B}; I_B < 0.1 \text{ mKA}$	SOD-123	K•A
J3	MMSZ5248BT1	ON	dz	$V_Z(I_{ZI} = 7.0 \text{ mA}) = 17.118.9 \text{ B}; I_B < 0.1 \text{ mkA}$	SOD-123	K•A
J4	MMSZ5249	VISH	dz	$V_Z(I_{ZT} = 6.6 \text{ mA}) = 19 \text{B}; I_B < 0.1 \text{ mKA}$	SOD-123	K • A
J5	MMSZ5250	VISH	dz	$V_2(I_{21}=6.2 \text{ mA})=20 \text{ B}; I_8 < 01 \text{ m/sA}$	SOD-123	K•A
J5	MMSZ5250BT1	ON	dz	$V_7(I_{27} = 6.2 \text{ mA}) = 19.021.0 \text{ B}; I_9 < 01 \text{ m/KA}$	SOD-123	K•A
JP	CMDZ4L3	CSI	dz	V ₂ (I ₂₁ = 0.5 mA) = 4.3B; P _D < 250 mBt	SOD-323, SC-76	K•A
K	BAT68-03W	INF	shd	V _B <8 B; I _E < 130 мA; V _E (I _E = 10 мA)< 0.5 B; I _B < 0.1 мкA; C _D < 1.0 пФ	SOD-323, SC-76	K•A
K1	MMSZ5251	VISH	dz	$V_Z(I_{ZT}=5.6 \text{ mA}) = 22 \text{ B}; I_B < 0.1 \text{ mkA}$	SOD-123	K•A
K1	MMSZ5251BT1	ON	dz	$V_2(I_{21} = 5.6 \text{ mA}) = 20.923.1 \text{ B}; I_8 < 0.1 \text{ m/sA}$	SOD-123	K•A
K2	MMSZ5252	VISH	dz	$V_2(I_{ZI} = 5.2 \text{ mA}) = 24 \text{ B}; I_B < 0.1 \text{ mKA}$	SOD-123	K•A
K2	MMSZ5252BT1	ON	dz	V _Z (I _{ZT} = 5.2 mA) = 22.825.2B; I _B < 0.1 mkA	SOD-123	K•A
K3	MMSZ5253	VISH	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 25 \text{B}; I_B < 0.1 \text{ mkA}$	SOD-123	K•A
K3	MMSZ5253BT1	ON	dz	V _Z (I _{ZT} =5.0 mA) = 23.7526.25 B; I _B < 0.1 mrA	SOD-123	K•A
K4	MMSZ5254	VISH	dz	$V_7(I_{77} = 4.6 \text{ mA}) = 27 \text{B}; I_8 < 0.1 \text{ m/sA}$	SOD-123	K•A
K4	MMSZ5254BT1	ON	dz	$V_7(I_{77} = 5.0 \text{ mA}) = 25.6528.35 \text{ B}; I_8 < 0.1 \text{ m/sA}$	SOD-123	K•A
K5	MMSZ5255	VISH	dz	$V_Z(I_{ZI} = 4.5 \text{ mA}) = 28 \text{ B}; I_B < 0.1 \text{ mKA}$	SOD-123	K•A
K5	MMSZ5255BT1	ON	dz	V _Z (I _{ZT} = 4.5 mA) = 26.629.4 B; I _B < 0.1 mKA	SOD-123	K•A
KP	CMDZ4L7	CSI	dz	$V_Z(I_{ZT}=0.5 \text{ mA}) = 4.7 \text{B}; P_D < 250 \text{ mB}T$	SOD-323, SC-76	K•A
L	BAT62-03W	INF	shd	$V_B < 40 \text{ B}; I_F < 20 \text{ mA}; V_F (I_F = 2 \text{ mA}) < 1 \text{ B}; I_B < 10 \text{ mkA}; C_D < 0.6 \text{ n}\Phi$	SOD-323, SC-76	K•A
L2	BAT42W	WTE	shd	V _B <30 B; I _F <200 мA; V _F (I _F =50 мA)<0.65 мB; C _D =10 пФ	SOD-123	K∙A
L2	BAT42W	VISH	shd	V _B <30 B; I _F <200 мA; V _F (I _F =50 мA)<0.65 мB; C _D =10 пФ	SOD-123	K•A
L2	BAT42WS	WTE	shd	V _B < 30 B; I _C < 200 мА; V _E (I _C = 50 мА) < 0.65 мВ; C _D = 10 пФ	SOD-323, SC-76	K•A
12	BAT42WS	PANJIT	shd	V _B < 30 B; I _E < 200 mA; V _E (I _E = 10 mA) < 0.4 mB	SOD-323, SC-76	K•A
L3	BAT43W	WTE	shd	V _B <30B; I _E <200mA; V _E (I _E =15 mA)<0.45mB; C _D =10 пФ	SOD-123	K•A
L3	BAT43W	VISH	shd	V _B <30 B; I _F <200 мA; V _F (I _F =15 мA)<0.45 мB; C _D =10 пФ	SOD-123	K•A





Код	Типономинал	Б	Φ	Особенности	Kopnyc	Ц:1•
.3	BAT43WS	WTE	shd	$V_B < 30 \text{ B}; I_F < 200 \text{ mA}; V_F (I_F = 15 \text{ mA}) < 0.45 \text{ mB}; C_D = 10 \text{ n}\Phi$	SOD-323, SC-76	K•A
.3	BAT43WS	PANJIT	shd	$V_R < 30 \text{ B}; I_F < 200 \text{ mA}; V_F (I_F = 2 \text{ mA}) < 0.33 \text{ mB}$	SOD-323, SC-76	K • A
_4	BAT54WS	PANJIT	shd	V _R <30 B; I _F <200 mA; V _F (I _F =1 mA)<0.32 mB	SOD-323, SC-76	K • A
_6	BAT46W	VISH	shd	$V_R \le 100 \text{ B}; I_F \le 150 \text{ mA}; V_F (I_F = 10 \text{ mA}) \le 0.45 \text{ mB}; C_D = 10 \text{ n}$	SOD-123	K•A
-6	BAT46W	TSC	shd	$V_R < 100 \text{ B}; I_F < 150 \text{ mA}; V_F (I_F = 10 \text{ mA}) < 0.45 \text{ mB}; C_D = 10 \text{ n}\Phi$	SOD-123	K • A
.7	BAT17W	VISH	shd	$V_R < 4B$; $I_F < 30$ mA; $V_F (I_F = 10$ mA) < 0.6 B; $I_R < 0.25$ mkA; $C_D < 0.75$ n Φ	SOD-123	K•A
_P	CMDZ5L1	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 5.1 \text{ B}; P_D < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
М	BB512	SIEM	var	$V_R < 12B$; $I_F < 50 \text{ mA}$; $I_R < 0.02 \text{ mkA}$; $C_{1B} = 440520 \text{ n}\Phi$; $C_{1B}/C_{8B} > 15$	SOD-123	K•A
М (син)	BAR65-03W	INF	pin	$V_R < 30 \text{ B}; I_F < 100 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 1.0 \text{ B}; C_D < 0.9 \text{ n}\Phi$	SOD-323, SC-76	K•A
M1	MMSZ5256	VISH	dz	$V_Z(I_{ZT} = 4.2 \text{ mA}) = 30 \text{ B}; I_R < 0.1 \text{ m/sA}$	SOD-123	K•A
M1	MMSZ5256BT1	ON	dz	$V_Z(I_{ZT} = 4.2 \text{ mA}) = 28.531.5 \text{ B; } I_R < 0.1 \text{ m/sA}$	SOD-123	K•A
M2	MMSZ5257	VISH	dz	$V_Z(I_{ZT} = 3.8 \text{ mA}) = 33 \text{ B; } I_R < 0.1 \text{ mrA}$	SOD-123	K•A
M2	MMSZ5257BT1	ON	dz	$V_Z(I_{ZT} = 3.8 \text{ mA}) = 31.3534.65 \text{ B}; I_R < 0.1 \text{ mkA}$	SOD-123	K•A
M3	MMSZ5258	VISH	dz	$V_Z(I_{ZT} = 3.4 \text{ mA}) = 36 \text{ B; } I_R < 0.1 \text{ mKA}$	SOD-123	K•A
M3	MMSZ5258BT1	ON	dz	$V_Z(I_{ZT} = 3.4 \text{ mA}) = 34.237.8 \text{ B; } I_R \le 0.1 \text{ m/s}.$	SOD-123	K • A
M4	MMSZ5259	VISH	dz	$V_Z(I_{ZT} = 3.2 \text{ mA}) = 39 \text{ B}; I_R < 0.1 \text{ mrA}$	SOD-123	K•A
M4	MMSZ5259BT1	ON	dz	$V_Z(I_{ZT}=3.2 \text{ mA})=37.0540.95 \text{ B; }I_R < 0.1 \text{ m/KA}$	SOD-123	K•A
M5	MMSZ5260	VISH	dz	$V_Z(I_{ZT} = 3.0 \text{ mA}) = 43 \text{ B}; I_R < 0.1 \text{ m/sA}$	SOD-123	K•A
M5	MMSZ5260BT1	ON	dz	$V_2(I_{ZT}=3.0 \text{ mA}) = 40.8545.15 \text{ B}; I_B < 0.1 \text{ mKA}$	SOD-123	K•A
N1	MMSZ5261	VISH	dz	$V_2(I_{2T} = 2.7 \text{ mA}) = 47 \text{ B}; I_B < 0.1 \text{ m/sA}$	SOD-123	K•A
N1	MMSZ5261BT1	ON	dz	V ₂ (I _{ZT} = 2.7 mA) = 44.6549.35 B; I _B < 0.1 mkA	SOD-123	K•A
N2	MMSZ5262	VISH	dz	$V_2(I_{2T}=2.5 \text{ mA})=51 \text{ B}; I_8 < 0.1 \text{ mKA}$	SOD-123	K•A
N2	MMSZ5262BT1	ON	dz	$V_2(I_{ZT} = 2.5 \text{ mA}) = 48.4553.55 \text{ B}; I_8 < 0.1 \text{ mKA}$	SOD-123	K•A
N3	MMSZ5263	VISH	dz	$V_2(I_{ZT} = 2.2 \text{ mA}) = 56 \text{ B}; I_B < 0.1 \text{ m/sA}$	SOD-123	K•A
N3	MMSZ5263BT1	ON	dz	$V_2(I_{21} = 2.2 \text{ mA}) = 53.2058.80 \text{ B}; I_{8} < 0.1 \text{ mkA}$	SOD-123	K•A
N4	MMSZ5264	VISH	dz	$V_2(I_{2T} = 2.1 \text{ mA}) = 60 \text{ B}; I_B < 0.1 \text{ mKA}$	SOD-123	K•A
N4	MMSZ5264BT1	ON	dz	$V_2(I_{27} = 2.1 \text{ mA}) = 57.0063.00 \text{ B; } I_{10} < 0.1 \text{ m/sA}$	SOD-123	K•A
N5	MMSZ5265	VISH	dz	$V_2(I_{77} = 2.0 \text{ mA}) = 62 \text{ B}; I_0 < 0.1 \text{ m/sA}$	SOD-123	K•A
N5	MMSZ5265BT1	ON	dz	V ₂ (I _{ZT} = 2 mA) = 58.9065.10 B; I _B < 0.1 mrA	SOD-123	K•A
NP	CMDZ5L6	CSI	dz	$V_2(I_{27} = 0.5 \text{ mA}) = 5.6 \text{B}; P_D < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
0 (бел)	BAT14-03W	SIEM	shd	V _B <4B; I _F <90 мA; V _F (I _F =10 мA)<0.66 мB; C _D <0.35 пФ	SOD-323, SC-76	K•A
OP .	CMDZ6L2	CSI	dz	$V_7(I_{27} = 0.5 \text{ mA}) = 6.2 \text{B}; P_0 < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
Р	BA586	INF	pin	V _B <50 B; I _F <50 мA; V _F (I _F =50 мA)<1.15 B; I _B <0.05 мкA; C _D <0.2 пФ	SOD-123	K•A
P	KV1841E	ТОКО	var	С=715пФ	SOD-323, SC-76	K•A
Р (бел)	BAT15-03W	INF	shd	V _B <4B; I _E <110 mA; V _E (I _E =10 mA)<0.41B; C _D <0.35 πΦ	SOD-323, SC-76	K•A
P1	BB131	PHIL	var	V _B >30 B; I _B (V _B =30 B)<0.01 мкА; С _{0.5 B} =817 пФ; С _{26 B} =0.71.055 пФ	SOD-323, SC-76	K•A
P1	MMSZ5266	VISH	dz	V ₂ (I _{2T} = 1.8 mA) = 68 B; I _B < 0.1 mrA	SOD-123	K•A
P1	MMSZ5266BT1	ON	dz	$V_z(I_{zz} = 1.8 \text{ mA}) = 64.6071.40 \text{ B; } I_R < 0.1 \text{ m/sA}$	SQD-123	K•A
P2	BB132	PHIL	var	V _B >30 B; I _B (V _B =30 B)<0.01 мкА; С _{0.5 B} =6075 пФ; С _{28 B} =2.32.75 пФ	SOD-323, SC-76	K•A
P2	MMSZ5267	VISH	dz	V ₂ (I _{ZT} = 1.7 mA) = 75 B; I ₈ < 0.1 mkA	SOD-123	K•A
P2	MMSZ5267BT1	ON	dz	V _Z (I _{ZT} = 1.7 mA) = 71.2578.75 B; I _B < 0.1 mkA	SOD-123	K•A
23	BB133	PHIL	var	$V_B > 30 \text{ B}; I_B (V_B = 30 \text{ B}) < 0.01 \text{ m/sA}; C_{0.5B} = 3846 \text{ n}\Phi; C_{28B} = 2.22.6 \text{ n}\Phi$	SOD-323, SC-76	K•A
23	BB133	LRC	var	V _B >30 B; I _B (V _B =30 B)< 0.01 мкА; С _{0.5.B} =3846 пФ; С _{28.B} =2.22.6 пФ	SOD-323, SC-76	K•A
93	MMSZ5268BT1	ON	dz	V ₂ (I _{2T} = 1.5 mA) = 77.986.1 B; I _B < 0.1 mrA	SOD-123	K•A
04	BB134	PHIL	var	V _B >30B; I _B (V _B =30B)<0.01 мкА; C _{0.5B} =17.521 пФ; C _{28B} =1.72.1 пФ	SOD-323, SC-76	K•A
04	BB134	LRC	var	V _B >30B; I _B (V _B =30B)<0.01 mKA; C _{0.5B} =17.521 nΦ; C _{28B} =1.72.1 nΦ	SOD-323, SC-76	K•A
04	MMSZ5269BT1	ON	dz	V ₂ (I _{2T} = 1.4 mA) = 82.6591.35 B; I _B < 0.1 mKA	SOD-123	K•A
25	BB135	PHIL	var	$V_B > 30 \text{ B} (I_B (V_B = 30 \text{ B}) < 0.01 \text{ m/s}, C_{0.5B} = 17.521 \text{ n}\Phi; C_{20B} = 1.72.1 \text{ n}\Phi$	SOD-323, SC-76	K•A
D5	BB135	LRC	var	$V_B > 30 \text{ B; } I_B (V_B = 30 \text{ B}) < 0.01 \text{ m/s}, C_{0.5B} = 17.521 \text{ n}\Phi; C_{28B} = 1.72.1 \text{ n}\Phi$	SOD-323, SC-76	K•A
D5	MMSZ5270BT1	ON	dz	$V_2(I_{\pi}=1.4 \text{ mA})=86.4595.55 \text{ B; }I_8<0.1 \text{ m/s}$	SOD-323, 30-70	K•A
		200	-		SOD-123 SOD-323, SC-76	K•A
P6	BB146	PHIL	var	$V_R > 30 \text{ B}; I_R (V_R = 30 \text{ B}) < 0.01 \text{ m/s}; C_{0.5 \text{ B}} = 3543 \text{ n}\Phi; C_{28 \text{ B}} = 1.72.1 \text{ n}\Phi$		





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PS	Код	Типономинал	6	Ф	Особенности	Корпус	Ц:1•2
PS	P8	BB148	PHIL	var	V _B >30 B; I _B (V _B = 30 B)< 0.02 мкА; С _{1 B} = 36.841.8 пФ; С _{2B B} = 2.42.75 пФ	SOD-323, SC-76	K∙A
PR	P 9	BB149	PHIL	var	$V_B > 30 \text{ B}; I_B (V_B = 30 \text{ B}) < 0.02 \text{ MKA}; C_{1B} = 1819.5 \text{ n}\Phi; C_{28B} = 1.92.25 \text{ n}\Phi$	SOD-323, SC-76	K•A
Process Pro	P 9	BB149	LRC	var	$V_B > 30 \text{ B; } I_B (V_B = 30 \text{ B}) < 0.02 \text{ m/s}, C_{0.5 \text{ B}} = 1819.5 \text{ n}\Phi; C_{28 \text{ B}} = 1.92.25 \text{ n}\Phi$	SOD-323, SC-76	K•A
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	PA	BB151	PHIL	var	$V_B > 10B$; $I_B(V_B = 10B) < 0.01$ mrA; $C_{1B} = 15.417$ n Φ ; $C_{3B} = 9.911.3$ n Φ	SOD-323, SC-76	K•A
C ₃₉ = 2.861., 2.754ndb	PB	BB152	PHIL	var	V _B >32 B; I _B (V _B =30 B)< 0.01 мкА; С _{1 B} =5262 пФ; С _{28 B} =2.482.89 пФ	SOD-323, SC-76	K•A
C2 220°-22' 55. 26 7 r Φ C2 22°-22' 55. 26 7 r Φ C2 22°-22' 55. 26 7 r Φ RPG BB157 PHIL var V _R > 10B ₁ -I ₁ (V _R = 10B ₁ <0.01 mA ₁ , C ₁₈ = 14.417 8 r Φ, C ₂₈ = 2.42278 r Φ S0D-323, SC-76 K + A RPG BB159 PHIL var V _R > 30B ₁ -I ₁ (V _R = 30B ₁ <0.01 mA ₂ , C ₁₈ = 36.841 8 r Φ, C ₂₈₈ = 2.42278 r Φ S0D-323, SC-76 K + A RPG BB159 PHIL var V _R > 30B ₁ -I ₁ (V _R = 30B ₁)<0.01 mA ₂ , C ₁₈ = 3.618 r Φ, C ₂₈₈ = 2.42278 r Φ S0D-323, SC-76 K + A RPG BB159 PHIL var V _R > 30B ₁ -I ₁ (V _R = 30B ₁)<0.01 mA ₂ , C ₁₈ = 1.8.19 5 r Φ, C ₂₈₈ = 1.92 r Φ PL BB159 PHIL var V _R > 30B ₁ -I ₁ (V _R = 30B ₁)<0.01 mA ₂ , C ₁₈ = 1.8.22126 r Φ C288 - 1.85 12 22.25 r Φ C288 - 1.85 12 22.25 r Φ C288 - 1.85 12 22.26 r Φ C	PC	BB153	PHIL	var		SOD-323, SC-76	K∙A
PRI BB157 PHIL Var V _R > 30 B, I ₁ (V _R = 30 B) < 0.01 m/A, C ₁ = 37 543 8 m/b, C ₂₈ = 2.4.22.76 m/b	PE	BB155	PHIL	var	$V_R > 10B$; $I_R(V_R = 10B) < 0.01$ mkA; $C0.34V = 45.249.8$ n Φ ; $C2.82V = 24.5526.7$ n Φ	SOD-323, SC-76	K∙A
PH BB 158 PHIL var V _R > 30 E, I ₁ (V _B = 30 B) < 0.01 m/d, C ₁ = 36 B41 B rdp, C ₂₈ = 2.42 75 m/p	PF	BB156	PHIL	var	$V_B > 10B$; $I_B(V_B = 10B) < 0.01$ mKA, $C_{1B} = 14.417.6$ n Φ ; $C_{4B} = 7.69.6$ n Φ	SOD-323, SC-76	K•A
Property	PG	BB157	PHIL	var	$V_B > 30 B$; $I_B (V_B = 30 B) < 0.01 \text{ m/sA}$; $C_{1B} = 37.543.8 \text{ n}\Phi$; $C_{28B} = 2.422.76 \text{ n}\Phi$	SOD-323, SC-76	K∙A
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	PH	BB158	PHIL	var	$V_R > 30 \text{ B; } I_R (V_R = 30 \text{ B}) < 0.01 \text{ m/sA; } C_{1B} = 36.841.8 \text{ n/p}; C_{2BB} = 2.42.75 \text{ n/p}$	SOD-323, SC-76	K◆A
PH. BB149A PHIL Var	P.J	BB159	PHIL	var	$V_B > 30 B; I_B (V_B = 30 B) < 0.01 \text{ m/sA}; C_{1B} = 1819.5 \text{ n}\Phi; C_{28B} = 1.92.25 \text{ n}\Phi$	SOD-323, SC-76	K+A
$ \begin{array}{c} C_{289} = 1.951, \ 2.225 \text{ riph} \\ \hline PMM & BB 154 & PHIL. \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$	PK	BB164	PHIL	var	V _B >30 B; I _B (V _B =30 B)< 0.01 мкА; С _{1 B} =6276 пФ; С _{28 B} =2.93.4 пФ	SOD-323, SC-76	K•A
PN BB190 PHIL Var Var V _R > 10 B) (E V _R = 10 B) < 0.003 mA/c C ₁₈ = 1820 rdy; C _{4.8} = 10.111.6 rdy SOD-323, SC-76 K × A PP CMDZ6L8 SSI dz V _x (U _x = 0.5 mA) = 6.8 B, P ₀ < 250 mB1 SOD-323, SC-76 K × A R (6m) BA695 INF pin V _R > 50B, I _k < 50 mA) = 7.5 B, P ₀ < 250 mB1 SOD-323, SC-76 K × A R (6m) BA695 INF pin V _R > 50B, I _k < 50 mA, V _R (I _k = 50 mA) < 1.1 B, I _h < 0.02 mA SOD-323, SC-76 K × A R (6m) BA695 INF pin V _R > 50B, I _k < 50 mA, V _R (I _k = 50 mA) < 1.1 B, I _h < 0.02 mA SOD-323, SC-76 K × A R (6m) BA695 INF pin V _R > 50B, I _k < 10 0 mA × (1.1 B, I _h < 0.02 mA SOD-323, SC-76 K × A R (6m) BA695 INF pin V _R > 50B, I _k < 10 0 mA × (1.1 B, I _h < 0.02 mA SOD-323, SC-76 K × A R (6m) BA695 INF pin V _R × 50B, I _k < 10 0 mA × (I _k = 10 0 mA) < 1.0 B, I _h < 0.02 mA SOD-323, SC-76 K × A S BA682 INF dt V _K × 30 B, I _k < 20 mA, I _h < 0.01 mA S S BB619 SIEM var V _R × 30B, I _k < 20 mA, I _h < 0.01 mA S S BB619 SIEM var V _R × 30B, I _k < 20 mA, I _h < 0.01 mA S C S BB619 SIEM var V _R × 30B, I _k < 20 mA, I _h < 0.01 mA S C S BB619 SIEM var V _R × 30B, I _k < 20 mA, I _h < 0.01 mA S C S BB620 SIEM var V _R × 30B, I _k < 20 mA, I _h < 0.01 mA S C S BB630 SIEM var V _R × 30B, I _k < 20 mA, I _h < 0.01 mA S C S BB630 SIEM var V _R × 30B, I _k < 20 mA, I _h < 0.01 mA S C S S BB630 SIEM var V _R × 30B, I _k < 20 mA, I _h < 0.01 mA S C S S S S S S S S S S S S S S S S S S	PL	BB149A	PHIL	var	$V_R > 30 B$; $I_R (V_R = 30 B) < 0.02$ мкА; $C_{1B} = 18.2221.26$ п Φ ; $C_{28B} = 1.9512.225$ п Φ	SOD-323, SC-76	K∙A
PP CMDZ6L8 CSI dz V ₂ (L ₂ = 0.6 MA) = 6.8 B, P ₀ < 250 MB1 SCD-323, SC-76 K + A CP CMDZ7L5 CSI dz V ₂ (L ₂ = 0.6 MA) = 7.5 B, P ₀ < 250 MB1 SCD-323, SC-76 K + A CR CMDZ7L5 CSI dz V ₂ (L ₂ = 0.6 MA) = 7.5 B, P ₀ < 250 MB1 SCD-323, SC-76 K + A CR CMDZ7L5 CSI dz V ₂ (L ₂ = 0.5 MA) = 7.5 B, P ₀ < 250 MB1 SCD-323, SC-76 K + A CR CMDZ8L2 CSI dz V ₂ (L ₂ = 0.5 MA) = 10.4 S, 11.5 B, I ₁ < 0.1 kmA SCD-323, SC-76 K + A CR CMDZ8L2 CSI dz V ₂ (L ₂ = 0.5 MA) = 8.2 B, P ₀ < 250 MB1 SCD-323, SC-76 K + A CR CMDZ8L2 CSI dz V ₂ (L ₂ = 0.5 MA) = 8.2 B, P ₀ < 250 MB1 SI ₁ = 100 MA < 1.0 B, I ₁ < 0.02 kmA, C ₀ < 1.1 mΦ SCD-323, SC-76 K + A CR S A6892 NP dvar V ₆ × 30 B, I ₁ < 20 MA I ₁ × (0.0 kmA, C ₁₀ = 17.5, 20 mΦ, C ₁₀ C ₂₈₀ = 8.29 8 SOD-123 K + A CR S BB619 SIEM var V ₆ × 30 B, I ₁ < 20 MA I ₁ × (0.0 kmA, C ₁₀ = 17.5, 20 mΦ, C ₁₀ C ₁₀ C ₂₈₀ = 13.5 SOD-123 K + A CR S BB619 SIEM var V ₆ × 30 B, I ₁ < 20 MA I ₁ × (0.0 kmA, C ₁₀ = 3042 mΦ, C ₁₀ C ₁₀ C ₂₈₀ = 13.5 SOD-123 K + A CR S BB619 SIEM var V ₆ × 30 B, I ₁ < 20 MA I ₁ × (0.0 kmA, C ₁₀ = 17.5, 20 mΦ, C ₁₀ C ₁₀ C ₂₈₀ = 13.5 SOD-123 K + A CR S BB620 SIEM var V ₆ × 30 B, I ₁ < 20 MA I ₁ × (0.0 kmA, C ₁₀ = 17.5, 20 mΦ, C ₁₀ C ₂₈₀ = 19.5,25 SOD-123 K + A CR S (60a) BB630 NP var V ₆ × 30 B, I ₁ < 20 MA I ₁ × (0.0 kmA, C ₁₀ = 17.5,20 mΦ, C ₁₀ C ₂₈₀ = 2.9	PM	BB154	PHIL	var	V _B >30 B; I _B (V _B =30 B)< 0.01 мкА; С _{1 B} = 18.521.25 пФ; С _{28 B} = 1.92.2 пФ	SOD-323, SC-76	K∙A
CP CMD27L5 CS d2 V ₂ (U ₂₇ = 0.5 MA) = 7.5 B, P _D < 250 MB; r 50 MA; V ₂ (U ₂₇ = 0.5 MA) = 7.5 B, P _D < 250 MB; r 50 MA; V ₂ (U ₂₇ = 0.5 MA) = 7.5 B, P _D < 250 MB; r 50 MA; V ₂ (U ₂₇ = 0.5 MA) = 7.5 B, V ₂ < 0.5 MB; r 50 MB; V ₂ (U ₂₇ = 0.5 MA) = 7.5 B, V ₃ < 0.1 MMA S25272BT1 CN dz V ₂ (U ₂₇ = 0.5 MA) = 10.5 L, 11.5 S, V ₃ < 0.1 MMA S25272BT1 CN dz V ₂ (U ₂₇ = 0.5 MA) = 8.2 B, P _D < 250 MB; r 50 MA; V ₃ < 0.1 MMA S25272BT1 CN dz V ₂ (U ₂₇ = 0.5 MA) = 8.2 B, P _D < 250 MB; r 50 MB; V ₃ < 0.0 MMA S25272BT1 CN dz V ₄ (U ₂₇ = 0.5 MA) = 8.2 B, P _D < 250 MB; V ₃ < 0.0 MMA S25272BT1 CN dz V ₄ (U ₂₇ = 0.5 MA) = 8.2 B, P _D < 250 MB; V ₃ < 0.0 MMA CD S1 MMA; CD S2 MMA;	PN	BB190	PHIL	var	$V_B > 10 \text{ B}; I_B (V_B = 10 \text{ B}) < 0.003 \text{ mrA}; C_{1B} = 1820 \text{ m}\Phi; C_{4B} = 10.111.6 \text{ m}\Phi$	SOD-323, SC-76	K•A
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	PP	CMDZ6L8	CSI	dz	$V_Z(I_{ZT}=0.5 \text{ mA}) = 6.8 \text{ B}; P_D < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
MMSZ6778T1 CN dz V ₂ (t ₂₇ = 1.1 MA) = 104.5	QP	CMDZ7L5	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 7.5 \text{ B}; P_D < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K∙A
SC September	R (бел)	BA595	INF	pin	$V_B > 50 B$; $I_F < 50 mA$; $V_F (I_F = 50 mA) < 1.1 B$; $I_B < 0.02 mkA$	SOD-323, SC-76	K∙A
S B8582 INF	R2	MMSZ5272BT1	ON	dz	$V_Z(I_{ZT} = 1.1 \text{ mA}) = 104.5115.5 \text{ B}; I_B < 0.1 \text{ mKA}$	SOD-123	K∙A
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	RP	CMDZ8L2	CSI	dz	$V_Z(I_{Z1} = 0.5 \text{ mA}) = 8.2 \text{B}; P_D < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K∙A
S B8619 SIEM Var V _R ⟨ 30 B ₁ ← 20 mA ₁ I ₈ < 0.01 mA ₂ C _{1B} = 3642 rΦ; C _{1B} (C _{2BB} > 13.5 SOD-123 K + A S B8619C SIEM Var V _R ⟨ 30 B ₁ ← 20 mA ₁ I ₈ < 0.01 mA ₂ C _{1B} = 3642 rΦ; C _{1B} (C _{2BB} > 13.5 SOD-123 K + A S (66a) B8620 SIEM Var V _R ⟨ 30 B ₁ ← 20 mA ₁ I ₈ < 0.01 mA ₂ C _{1B} = 6276 rΦ; C _{1B} (C _{2BB} = 19.525 SOD-123 K + A S (66a) B8635 INF Var V _R ⟨ 30 B ₁ ← 20 mA ₁ I ₈ < 0.01 mA ₂ C _{1B} = 6276 rΦ; C _{1B} (C _{2BB} = 19.525 SOD-123 K + A S (xem) B8639 INF Var V _R ⟨ 30 B ₁ ← 20 mA ₁ I ₈ < 0.01 mA ₂ C _{1B} = 71.520 rΦ; C _{1B} (C _{2BB} = 14.7 SOD-323, SC-76 K + A S (xem) B8639 INF Var V _R ⟨ 30 B ₁ ← 20 mA ₁ I ₈ < 0.01 mA ₂ C _{1B} = 3640 rΦ; C _{1B} (C _{2BB} = 14.7 SOD-323, SC-76 K + A S (xem) B8639 INF Var V _R ⟨ 30 B ₁ ← 20 mA ₁ I ₈ < 0.01 mA ₂ C _{1B} = 3640 rΦ; C _{1B} (C _{2BB} = 14.7 SOD-323, SC-76 K + A S (xem) B8639 INF Var V _R ⟨ 30 B ₁ ← 20 mA ₁ I ₈ < 0.01 mA ₂ C _{1B} = 3642 rΦ; C _{1B} (C _{2BB} = 14.7 SOD-323, SC-76 K + A S (xem) B8639 INF Var V _R ⟨ 30 B ₁ ← 20 mA ₁ I ₈ < 0.01 mA ₂ C _{1B} = 3642 rΦ; C _{1B} (C _{2BB} = 183 SOD-323, SC-76 K + A S (xem) B8639 INF Var V _R ⟨ 30 B ₁ ← 20 mA ₁ I ₈ < 0.01 mA ₂ C _{1B} = 3642 rΦ; C _{1B} (C _{2BB} = 183 SOD-323, SC-76 K + A S (xem) B8639 INF Var V _R ⟨ 30 B ₁ ← 20 mA ₁ I ₈ < 0.01 mA ₂ C _{1B} = 3642 rΦ; C _{1B} (C _{2BB} = 183 SOD-323, SC-76 K + A S (xem) B8639 INF Var V _R ⟨ 30 B ₁ ← 20 mA ₁ I ₈ < 0.01 mA ₂ C _{1B} = 3042 mA ₂ < 0.02 mA ₂ SOD-323, SC-76 K + A S (xem) B8639 INF V _R (1B S D M ₂ V ₁ (I _{1B} = 10 mA ₁) < 0.02 mA ₂ SOD-323, SC-76 K + A S (xem) B8630 INF V _R (1B S D M ₂ V ₁ (I _{1B} = 10 mA ₁) < 0.02 mA ₂ SOD-323, SC-76 K + A S (xem) B8640 INF V _R (1B S D M ₂ V ₁ (I _{1B} = 10 mA ₁) < 0.02 mA ₂ SOD-323, SC-76 K + A S S S S S S S S S S S S S S S S S S	S	BA582	INF	dtv	$V_B < 35 B$; $I_F < 100 \text{ mA}$; $V_F (I_F = 100 \text{ mA}) < 1.0 B$; $I_B < 0.02 \text{ mrA}$; $C_D < 1.1 \text{ n}$	SOD-123	K∙A
S BB619C SIEM var V _R < 30 B ₁ k < 20 mA ₁ k ₁ < 0.01 mA ₂ C ₁₁₀ = 36. A2 r0¢; C ₁₁₀ C ₂₀₀ ≥ 13.5 SOD-123 K ≠ A SOD-123	S	BB515	SIEM	var	$V_B < 30 \text{ B}; I_F < 20 \text{ mA}; I_B < 0.01 \text{ m/sA}; C_{1B} = 17.520 \text{ n}\Phi; C_{1B}/C_{28B} = 8.29.8$	SOD-123	K•A
S BB619C SIEM var V _R < 30 B ₁ k < 20 mA ₁ k ₁ < 0.01 mA ₂ C ₁₁₀ = 36. A2 r0¢; C ₁₁₀ C ₂₀₀ ≥ 13.5 SOD-123 K ≠ A SOD-123	S	BB619	SIEM	var	$V_B < 30 \text{ B}; I_C < 20 \text{ mA}; I_D < 0.01 \text{ m/KA}; C_{1B} = 3642 \text{ n}\Phi; C_{1B}/C_{26B} > 13.5$	SOD-123	K•A
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	S	BB619C	SIEM	var		SOD-123	K•A
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	S	BB620	SIEM	var		SOD-123	K•A
\$ (xem) BB639 INF var V _R < 30 B ₁ k < 20 mA ₁ k ₁ < 0.01 mArX, C _{1B} = 3640 rФ; C _{1B} (C _{2BB} = 14.7 S.DD.323, SC-76 K. + A (xem) BB639C INF var V _R < 30 B ₁ k < 20 mA ₁ k ₁ < 0.01 mArX, C _{1B} = 36.542 rΦ; C _{1B} C _{2BB} = 15.3 S.DD.323, SC-76 K. + A (xem) BB640 INF var V _R < 30 B ₁ k < 20 mA ₁ k ₁ < 0.01 mArX, C _{1B} = 36.742 rΦ; C _{1B} C _{2BB} = 15.3 S.DD.323, SC-76 K. + A (xem) BB640 INF var V _R < 30 B ₁ k < 20 mA ₁ k ₁ < 0.01 mArX, C _{1B} = 3276 rΦ; C _{2BB} = 2.83.3 S.DD.323, SC-76 K. + A (xem) BB640 INF var V _R < 30 B ₁ k < 20 mA ₁ k ₁ k ₁ = 10 mA ₂ < 0.01 B ₁ k ₁ < 0.02 mArX S.DD.323, SC-76 K. + A (xem) S.SD.323, SC-76 S.DD.323, SC-76 K. + A (xem) S.DD.323, SC-76 S.DD.323, S	S (бел)	BB535	INF	var		SOD-323, SC-76	K•A
S(xen) BB639C INF var V _R × 30 B ₁ k < 20 MA ₁ k ₁ < 0.01 MAX, C _{1B} = 36.542 n D; C _{1B} C _{2BB} = 15.3 SCD-323, SC-76 K + A S(xpa) BB640 INF var V _R × 30 B ₁ k < 20 MA ₁ k ₁ < 0.01 MAX, C _{1B} = 6276 n D; C _{2B} = 2.833 SCD-323, SC-76 K + A S(xpa) BB640 INF var V _R × 35 B ₁ k < 10 0 MA ₁ × (1.0 B ₁ k ₁ < 0.02 MAA SCD-323, SC-76 K + A S(xpa) B6522 INF dtv V _R × 35 B ₁ k ₁ < 10 0 MA ₂ V ₁ (k ₁ = 100 MA) < 1.0 B ₁ k ₁ ∨ 0.02 MAA SCD-323, SC-76 K + A S(xpa) SCD-323, SC-76 SC-76 SC-76 SCD-323, SC-76 SC-76 SC-76 SCD-323, SC-76 SC-76 SC-76 SC-76 SCD-323, SC-76 SC	S (жел)	BB639	INF	var		SOD-323, SC-76	K•A
\$ (pa) BB640 INF var V _R < 30 B ₁ k < 20 mA, k ₁ < 20 1 mAc, k ₁ = 6276 nФ; C _{SS} = 2 83 3 SOD-323, SC-76 K = A	S (жел)	BB639C	INF	var		SOD-323, SC-76	K•A
$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	S (kpa)	BB640	INF	var		SOD-323, SC-76	K•A
\$2	S (син)	BA592	INF	dtv		SOD-323, SC-76	K•A
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	S2	1SS315	TOSH	shd		SOD-323, SC-76	K•A
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	S3	1SS357	TOSH	shd	V _B >40B; V _E (I _E = 100 mA) < 0.6B; I _B (V _B = 40B) < 5 mkA	SOD-323, SC-76	K•A
\$68 \$D103AW VISH \$hd \$V_R < 40 B; V_E (I_E = 200 MA) < 0.6 B; C_0 = 50 n Φ\$	S4	1SS367	TOSH	shd		SOD-323, SC-76	K•A
\$68 \$\ \text{SD}\$ \ \text{103AW} \ \ \text{VisH} \ \ \ \text{shd} \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	S5		TOSH	shd	The second secon		K•A
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	S6	SD103AW	VISH	shd		1/0x 1/0/00 100 100 100 100 100 100 100 100	K•A
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	S7	BAT42W	DIODS	shd		SOD-123	K•A
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	S7	BAT42W	TSC	shd	1 1 1 1 1 1	SOD-123	K•A
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	S7	BAT42WS	DIODS	shd		SOD-323, SC-76	K•A
$\begin{array}{llllllllllllllllllllllllllllllllllll$	S7	SD103BW	VISH	shd	The state of the s	SOD-123	K•A
$\begin{array}{llllllllllllllllllllllllllllllllllll$	S8	BAT43W	DIODS	shd			K•A
$\begin{array}{llllllllllllllllllllllllllllllllllll$	S8	BAT43W	TSC	shd		SOD-123	K•A
$\begin{array}{llllllllllllllllllllllllllllllllllll$	S8	BAT43WS	DIODS	shd	N 21 222 2 2 2		K•A
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	S8	SD103CW	VISH	shd	- 11 - 11 - 11 - 11 - 11 - 11 - 11 - 1	SOD-123	K•A
SA SD101AW VISH shd V _R < 60 B; F < 30 MA; V _F (I _F = 15 MA) < 1.0 B; C _D < 2 r/Φ SOD-123 K + A SB BA75AT1 ON shd V _R < 30 B; F < 200 MA; V _F (I _F = 30 MA) < 0.5 B; I _{RC} < 5.5 tc	S9	511000000000000000000000000000000000000				500000000000000000000000000000000000000	
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	SA		2770007777		The state of the s	100000000000000000000000000000000000000	K•A
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	SB					100000000000000000000000000000000000000	K•A
$ \begin{array}{llllllllllllllllllllllllllllllllllll$	SB		300			100000000000000000000000000000000000000	K•A
SP CMDZ9L1 CSI dz $V_Z(I_{ZT} = 0.5 \text{ mA}) = 9.1 \text{B}; P_D < 250 \text{ mB} \text{T}$ SOD-323, SC-76 K \bullet A	SC				1 11 11 11 11 11		K•A
72/21	SP				1 1 1 1 1 1 1		K•A
	Т	200000000000000000000000000000000000000					K•A





Код	Типономинал	6	Φ	Особенности	Корпус	Ц:1•2
Т (син)	BAR67-03W	INF	pin	$V_R \le 150 \text{ B; } I_E \le 200 \text{ mA; } V_E (I_E = 50 \text{ mA}) \le 1.2 \text{ B; } C_D \le 0.9 \text{ n}\Phi$	SOD-323, SC-76	K∙A
T1	GDZ5V1B	VISH	dz	$V_z = 5.1 \text{ B}; Z_{Z1} (I_z = 5 \text{ mA}) = 80 \text{ Om}$	SOD-323, SC-76	K∙A
T2	GDZ5V6B	VISH	dz	V _Z =5.6 B; Z _{ZT} (I _Z =5 mA) = 60 Om	SOD-323, SC-76	K•A
Т3	GDZ6V2B	VISH	dz	$V_2 = 6.2 \text{ B}; Z_{ZT} (I_2 = 5 \text{ mA}) = 60 \text{ Om}$	SOD-323, SC-76	K∙A
T4	GDZ6v8B	VISH	dz	Vz = 6.8 B; Zzt (Iz = 5 mA) = 40 Om	SOD-323, SC-76	K∙A
T 5	GDZ7V5B	VISH	dz	V _z =7.5 B; Z _{ZT} (I _z =5 mA)=30 Om	SOD-323, SC-76	K∙A
T6	GDZ8V2B	VISH	dz	V _Z =8.2 B; Z _{Z1} (I _Z =5 mA) = 30 Om	SOD-323, SC-76	K∙A
T7	GDZ9V1B	VISH	dz	V ₂ =9.1 B; Z _{ZT} (I _Z =5 mA) = 30 Om	SOD-323, SC-76	K∙A
18 T	GDZ10B	VISH	dz	$V_z = 10 \text{ B}; Z_{zT}(I_z = 5 \text{ mA}) = 30 \text{ Om}$	SOD-323, SC-76	K∙A
T9	GDZ11B	VISH	dz	V _Z =11 B; Z _{ZT} (I _Z =5 мA)=300м	SOD-323, SC-76	K∙A
TA	GDZ12B	VISH	dz	V _Z =12B; Z _{ZT} (I _Z =5 мA)=300м	SOD-323, SC-76	K∙A
ТВ	GDZ13B	VISH	dz	$V_Z = 13 \text{ B}; Z_{ZT} (I_Z = 5 \text{ mA}) = 370 \text{ m}$	SOD-323, SC-76	K•A
TC	GDZ15B	VISH	dz	V _Z =15B; Z _{ZT} (I _Z =5 мA) = 42 Oм	SOD-323, SC-76	K∙A
TD	GDZ16B	VISH	dz	$V_2 = 16 \text{ B}; Z_{77}(I_2 = 5 \text{ mA}) = 50 \text{ Om}$	SOD-323, SC-76	K∙A
TE	GDZ18B	VISH	dz	V ₂ = 18 B; Z _{ZT} (I _Z = 5 mA) = 65 Om	SOD-323, SC-76	K•A
TH	GDZ20B	VISH	dz	V _Z = 20 B; Z _{ZT} (I _Z = 5 mA) = 85 Om	SOD-323, SC-76	K•A
TK	GDZ22B	VISH	dz	V ₂ =22B; Z _{2T} (I ₂ =5 MA) = 100 OM	SOD-323, SC-76	K•A
TL	GDZ24B	VISH	dz	$V_7 = 24 \text{ B; } Z_{77} (I_7 = 5 \text{ mA}) = 120 \text{ Om}$	SOD-323, SC-76	K∙A
TM	GDZ27B	VISH	dz	V ₇ =27B; Z ₇₇ (I ₂ =5 mA)=150 Om	SOD-323, SC-76	K•A
TN	GDZ30B	VISH	dz	V _Z =30 B; Z _{ZT} (I _Z =5 mA) = 200 Om	SOD-323, SC-76	K•A
TP	GDZ33B	VISH	dz	$V_z = 33 \text{ B}; Z_{zT}(I_z = 5 \text{ mA}) = 250 \text{ Om}$	SOD-323, SC-76	K•A
TT	GDZ36B	VISH	dz	V ₂ =36B; Z _{2T} (I ₂ =5 MA)=300 OM	SOD-323, SC-76	K•A
T1	MMSZ2V4T1	ON	dz	V ₂ (I ₂₇ = 5 mA) = 2.28 2.52 B; I _B < 50 mkA	SOD-123	K•A
T2	1SV215	TOSH	var	V _B >30 B; I _B (V _B =28 B)<0.01 мкА; С _{2 B} =2632 пФ; С _{25 B} =2.53.2 пФ	SOD-323, SC-76	K•A
T2	BAV19W	DIODS	di	$V_B \le 100 \text{ B}; I_E \le 250 \text{ mA}; V_E (I_E = 100 \text{ mA}) \le 1 \text{ B}; C_D \le 5 \text{ n}\Phi; t_{BB} \le 50 \text{ Hc}$	SOD-123	K•A
T2	BAV20W	DIODS	di	$V_B < 150 \text{ B; } I_E < 250 \text{ mA; } V_E (I_E = 100 \text{ mA}) < 1 \text{ B; } C_D < 5 \text{ n}\Phi; t_{BB} < 50 \text{ Hc}$	SOD-123	K•A
T2	BAV20W	TSC	di	V_B < 150 B; I_F < 400 mA; V_F (I_F = 100 mA)< 1 B; C_D < 5 n Φ ; t_{BB} < 50 Hc	SOD-123	K•A
T2	BAV20W	MCC	di	V _B <150 B; I _E <400 mA; V _E (I _E =100 mA)<1 B; C _D <5 nΦ; t _{BB} <50 Hc	SOD-123	K•A
T2	MMSZ2V7T1	ON	dz	$V_2(I_{ZT} = 5 \text{ mA}) = 2.572.84 \text{ B; } I_B < 20 \text{ m/sA}$	SOD-123	K•A
T3	1SV245	TOSH	var	V _B > 30 B; I _B (V _B = 28 B) < 0.01 мкА; С _{2B} = 3.314.55 пФ; С _{25B} = 0.610.77 пФ	SOD-323, SC-76	K•A
T3	BAV19W	DIODS	di	V _B <100 B; I _E <250 mA; V _E (I _E =100 mA)<1 B; C _D <5 nΦ; t _{BB} <50 Hc	SOD-123	K•A
T3	BAV20W	DIODS	di	$V_B < 150 \text{ B}; I_E < 250 \text{ mA}; V_E (I_E = 100 \text{ mA}) < 1 \text{ B}; C_D < 5 \text{ n}\Phi; t_{BB} < 50 \text{ Hc}$	SOD-123	K•A
T3	BAV21W	DIODS	di	V _B <200 B; I _E <250 мA; V _E (I _E =100 мA)<1B; C _D <5 пФ; t _{BB} <50 нс	SOD-123	K•A
T3	BAV21W	TSC	di	V _B <200 B; I _E <400 мA; V _E (I _E =100 мA)<1B; C _B <5 пФ; t _{BB} <50 нс	SOD-123	K•A
T3	BAV21W	MCC	di	V_B < 200 B; I_F < 400 mA; V_F (I_F = 100 mA) < 1 B; C_D < 5 n Φ ; t_{BB} < 50 Hc	SOD-123	K•A
T3	MMSZ3V0T1	ON	dz	$V_2(I_{TT}=5 \text{ mA}) = 2.853.15 \text{ B}; I_B < 10 \text{ m/sA}$	SOD-123	K∙A
T4	1N4148W	DIODS	sd	V _B =75 B; I _E =300 мA; P _D =350 мВт; t _{PB} <4 нс	SOD-123	K∙A
T4	1SV216	TOSH	var	V _B >30 B; I _B (V _B =28 B)<0.01 мкА; С _{2B} =10.516 пФ; С _{10B} =3.35.7 пФ	SOD-323, SC-76	K•A
T4	MMSZ3V3T1	ON	dz	V ₂ (I _{ZT} = 5 mA) = 3.143.47 B; I _B < 5 mKA	SOD-123	K•A
T5	1N4448W	DIODS	sd	V _B =75 B; I _F =500 mA; P _D =400 mBr; t _{FB} <4 hC	SOD-123	K∙A
T5	MMSZ3V6T1	ON	dz	V ₂ (I _{ZT} = 5 mA) = 3.423.78 B; I _B < 5 mKA	SOD-123	K∙A
16	1SV217	TOSH	var	V _B >30 B; I _B (V _B =28 B)<0.01 мкА; С _{2B} =3339 пФ; С _{25B} =2.63.2 пФ	SOD-323, SC-76	K∙A
17	1SV230	TOSH	var	V _B >30 B; I _B (V _B =28 B)< 0.01 мкА; С _{2B} =13.916.1 пФ; С _{20B} =1.72.1 пФ	SOD-323, SC-76	K•A
T8	1SV229	TOSH	var	V _B >15B; I _B (V _B =15B)<0.003 мкА; С _{2B} =1416 пФ; С _{10B} =5.56.5 пФ	SOD-323, SC-76	K•A
T9	1SV232	TOSH	var	V _B >30 B; I _B (V _B =28 B)< 0.01 мкA; C _{2 B} =2832 пΦ; C _{25 B} =2.753.1 пΦ	SOD-323, SC-76	K∙A
TA	1SV231	TOSH	var	V _B >30 B; I _B (V _B =28 B)<0.01 мкА; С _{2B} =4149.5пФ; С _{25B} =2.73.4 пФ	SOD-323, SC-76	K•A
TC	1SV239	TOSH	var	V _B >15B; I _B (V _B =15B)<0.003 мкА; С _{2B} =3.84.7 пФ; С _{10B} =1.52 пФ	SOD-323, SC-76	K•A
TD	1SV262	TOSH	var	$V_B > 34 \text{ B; } I_B (V_B = 32 \text{ B}) < 0.01 \text{ m/sA; } C_{2B} = 3338 \text{ n/p; } C_{25B} = 2.63 \text{ n/p}$	SOD-323, SC-76	K∙A
TE	1SV269	TOSH	var	V _B >34B; I _B (V _B =32B)< 0.01 мкА; С _{2B} =2934пФ; С _{25B} =2.52.9пФ	SOD-323, SC-76	K∙A
TF	1SV270	TOSH	var	V _B >10B; I _B (V _B =10B)<0.003 мкА; С _{1B} =1517 пФ; С _{4B} =7.38.7 пФ	SOD-323, SC-76	K∙A
TG	1SV271	TOSH	pin	V _B >50 B; I _E <50 mA; V _E (I _E =50 mA) < 1B; I _B <0.1 mkA	SOD-323, SC-76	K•A
TH	1SV293	TOSH	var	V _B > 10 B; I _B (V _B = 10 B)< 0.003 мкА; С _{1 B} = 1820 пФ; С _{4 B} = 10.111.6 пФ	SOD-323, SC-76	K•A





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Код	Типономинал	6	Ф	Особенности	Корпус	Ц:1•2
TI	1SV214	TOSH	var	$V_B > 30B;I_B(V_B = 28B) < 0.01$ мк $A;C_{2B} = 14.1616.25$ п $\Phi;C_{2B} = 2.112.43$ п Φ	SOD-323, SC-76	K∙A
TJ	1SV288	TOSH	var	$V_B > 30 \text{ B}; I_B (V_B = 28 \text{ B}) < 0.01 \text{ m/sA}; C_{2B} = 4149.5 \text{ n}\Phi; C_{25B} = 2.53.2 \text{ n}\Phi$	SOD-323, SC-76	K • A
TK	1SV287	TOSH	var	$V_B > 30 \text{ B; } I_B (V_B = 28 \text{ B}) < 0.01 \text{ m/sA; } C_{2B} = 4.25.7 \text{ n}\Phi; C_{25B} = 0.530.68 \text{ n}\Phi$	SOD-323, SC-76	K•A
TL	1SV276	TOSH	var	$V_R > 10 \text{ B; } I_R (V_R = 10 \text{ B}) < 0.003 \text{ m/kA; } C_{1B} = 1517 \text{ n}\Phi; C_{4B} = 78.5 \text{ n}\Phi$	SOD-323, SC-76	K•A
TO	1SV277	TOSH	var	$V_R > 10B$; $I_R(V_R = 10B) < 0.003$ mKA; $C_{1B} = 44.9$ n Φ ; $C_{4B} = 1.852.35$ n Φ	SOD-323, SC-76	K•A
TP	CMDZ10L	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 10 \text{ B}; P_D < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
Π	1SV302	TOSH	var	$V_R > 30 \text{ B; } I_R(V_R = 28 \text{ B}) < 0.01 \text{ m/sA; } C_{2B} = 4251 \text{ n/p; } C_{25B} = 2.13.1 \text{ n/p}$	SOD-323, SC-76	K•A
TV	1SV304	TOSH	var	$V_B > 10 \text{ B}; I_B (V_B = 10 \text{ B}) < 0.003 \text{ m/KA}; C_{1B} = 17.319.3 \text{ m}\Phi; C_{4B} = 5.36.6 \text{ m}\Phi$	SOD-323, SC-76	K•A
TX	1SV307	TOSH	pin	$V_B > 30 \text{ B; } I_E < 50 \text{ mA; } V_E (I_E = 50 \text{ mA}) < 1 \text{ B; } I_B < 0.1 \text{ mrA}$	SOD-323, SC-76	K•A
TY	1SS314	TOSH	di	$V_R \le 30 \text{ B}; I_E \le 100 \text{ mA}; V_E (I_E = 2 \text{ mA}) \le 0.85 \text{ B}; I_R \le 0.1 \text{ mKA}$	SOD-323, SC-76	K•A
U (бел)	BB545	INF	var	$V_R < 30 \text{ B; } I_F < 20 \text{ mA; } I_R < 0.01 \text{ m/sA; } C_{1B} = 18.521.5 \text{ n}\Phi; C_{1B}/C_{28B} = 911$	SOD-323, SC-76	K•A
U1	MMSZ3V9T1	ON	dz	V _Z (I _{Z1} =5 mA) = 3.714.10B; I _B < 3 mKA	SOD-123	K∙A
U2	MMSZ4V3T1	ON	dz	$V_Z(I_{ZI} = 5 \text{ mA}) = 4.094.52 \text{ B}; I_B < 3 \text{ m/KA}$	SOD-123	K•A
U3	MMSZ4V7T1	ON	dz	V _Z (I _{ZI} = 5 mA) = 4.474.94B; I _B < 2 mKA	SOD-123	K•A
U4	MMSZ5V1T1	ON	dz	$V_Z(I_{ZI} = 5 \text{ mA}) = 4.855.36 \text{ B}; I_B \le 1 \text{ m/sA}$	SOD-123	K•A
U5	MMSZ5V6T1	ON	dz	V _Z (I _{ZI} =5 mA) =5.325.88B; I _B <3 mrA	SOD-123	K•A
UP	CMDZ11L	CSI	dz	$V_z(I_{zz} = 0.5 \text{ mA}) = 11 \text{B}_z P_D < 250 \text{ mB}_T$	SOD-323, SC-76	K•A
V1	1SV310	TOSH	var	V _B >10 B; I _B (V _B = 10B)< 0.003 mkA; C _{1 B} =9.711.1 nΦ; C _{4 B} =4.455.45 nΦ	SOD-323, SC-76	K•A
V1	MMSZ6V2T1	ON	dz	V _Z (I _{ZT} = 5 mA) = 5.896.51B; I _R < 2 mKA	SOD-123	K•A
V2	1SV328	TOSH	var	$V_B > 10 \text{ B; } I_B (V_B = 10 \text{ B}) < 0.003 \text{ m/sA; } C_{1B} = 5.76.7 \text{ n} \Phi; C_{4B} = 1.852.45 \text{ n} \Phi$	SOD-323, SC-76	K•A
V2	MMSZ6V8T1	ON	dz	V _Z (I _{ZT} = 5 mA) = 6.467.14B; I _B < 1 mKA	SOD-123	K•A
V3	MMSZ7V5T1	ON	dz	V ₂ (I ₂₇ = 5 mA) = 7.137.88B; I ₈ < 0.7 mKA	SOD-123	K•A
V4	MMSZ8V2T1	ON	dz	V ₇ (I _{2T} = 5 mA) = 7.798.61B; I _B < 0.5 mkA	SOD-123	K•A
V5	MMSZ9V1T1	ON	dz	V ₂ (I ₂₁ = 5 mA) = 8.659.56B; I ₈ < 0.2 mkA	SOD-123	K•A
V6	1SV313	TOSH	var	$V_B > 10 \text{ B; } I_B (V_B = 10 \text{ B}) < 0.003 \text{ m/sA}; C_{0.5 \text{ B}} = 7.3 \dots 8.4 \text{ n}\Phi; C_{2.5 \text{ B}} = 2.75 \dots 3.4 \text{ n}\Phi$	SOD-323, SC-76	K•A
V7	1SV312	TOSH	var	$V_B > 10B$; $I_B(V_B = 10B) < 0.003$ mcA; $C_{1,B} = 26.529.5$ n Φ ; $C_{4,B} = 67.1$ n Φ	SOD-323, SC-76	K•A
V8	1SV324	TOSH	var	V _R >10B; I _R (V _R =10B)<0.003 mxA; C ₁ g=20.525.5πΦ; C ₄ g=9.212 πΦ	SOD-323, SC-76	K•A
VP	CMDZ12L	CSI	dz	V ₇ (I ₂₇ =0.5 MA) = 12B; P _D <250 MBT	SOD-323, SC-76	K•A
W1	BZT52B2V4	VISH	dz	V _Z (I _{ZT} = 5 mA) = 2.35 2.45B; Z _{ZT} < 85 Om	SOD-123	K•A
W1	BZT52C2V4	VISH	dz	V _Z (I _{ZT} =5 MA) =2.22.8 B; Z _{ZT} <85 OM	SOD-123	K•A
W1	BZT52C2V7S	DIODS	dz	V ₂ (I ₂₇ =5 MA) = 2.52.9 B; Z ₂₇ < 100 Om	SOD-323, SC-76	K•A
W1	BZX384B2V4	VISH	dz	$V_7(I_{27} = 5 \text{ MA}) = 2.352.45B; Z_{77} < 100 \text{ OM}$	SOD-323, SC-76	K•A
W1	BZX384C2V4	VISH	dz	$V_Z(I_{ZT} = 5 \text{ MA}) = 2.22.6 \text{ B}; Z_{ZT} \le 100 \text{ CM}$	SOD-323, SC-76	K•A
W2	BZT52B2V7	VISH	dz	$V_{z}(I_{zT} = 5 \text{ MA}) = 2.22.6 \text{ B}, Z_{zT} < 1000 \text{ M}$ $V_{z}(I_{zT} = 5 \text{ MA}) = 2.652.75 \text{ B}; Z_{zT} < 830 \text{ M}$	SOD-323, SC-76	K•A
W2	BZT52C2V7	VISH	dz	V ₂ (I ₂₇ = 5 mA) = 2.52.9B; Z ₂₇ < 83 Om	SOD-123	K•A
W2	BZT52C3V0S	DIODS	dz	$V_2(I_{Z1} = 5 \text{ MA}) = 2.83.2 \text{ B}, Z_{Z1} < 650 \text{ M}$ $V_2(I_{Z1} = 5 \text{ MA}) = 2.83.2 \text{ B}, Z_{Z1} < 950 \text{ M}$	SOD-323, SC-76	K•A
W2	BZX384B2V7	VISH	dz	$V_Z(I_{ZT} = 5 \text{ MA}) = 2.652.75 \text{ B}; Z_{ZT} \le 100 \text{ Om}$	SOD-323, SC-76	K•A
W2	BZX384C2V7	VISH	dz	$V_Z(I_{ZT} = 5 \text{ MA}) = 2.532.75 \text{ B}, Z_{ZT} \le 100 \text{ CM}$ $V_Z(I_{ZT} = 5 \text{ MA}) = 2.52.9 \text{ B}, Z_{ZT} \le 100 \text{ CM}$	SOD-323, SC-76	K•A
W3	BZT52B3V0	VISH	dz		SOD-323, SC-76	K•A
W3	BZT52C3V0	VISH	700	$V_Z(I_{ZT}=5 \text{ mA}) = 2.943.06 \text{ B}; Z_{ZT} < 95 \text{ Om}$ $V_Z(I_{ZT}=5 \text{ mA}) = 2.83.2 \text{ B}; Z_{ZT} < 95 \text{ Om}$	SOD-123	K•A
W3	BZT52C3V0	DIODS	dz			_
			dz	V _Z (I _{ZT} = 5 mA) = 3.13.5 B; Z _{ZT} < 950 m	SOD-323, SC-76	K•A
W3	BZX384B3V0	VISH	dz	V _z (I _{z1} =5 mA) = 2.943.06B; Z _{z1} <95 0m	SOD-323, SC-76	K•A
W3	BZX384C3V0	VISH	dz	V _Z (I _{ZT} = 5 mA) = 2.83.2 B; Z _{ZT} < 95 Om	SOD-323, SC-76	K•A
W4	BZT52B3V3	VISH	dz	V _Z (I _{ZT} =5 mA) = 3.233.37B; Z _{ZT} <95 Om	SOD-123	K•A
W4	BZT52C3V3	VISH	dz	V _Z (I _{ZT} = 5 mA) = 3.13.5 B; Z _{ZT} < 950 m	SOD-123	K•A
W4	BZT52C3V6S	DIODS	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 3.43.8 \text{ B}; Z_{ZT} < 900 \text{ m}$	SOD-323, SC-76	K•A
W4	BZX384B3V3	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA})=3.233.37B; Z_{ZT}<95 \text{ Om}$	SOD-323, SC-76	K•A
W4	BZX384C3V3	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA})=3.13.5 \text{ B}; Z_{ZT}<95 \text{ Om}$	SOD-323, SC-76	K•A
W5	BZT52B3V6	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA})=3.533.67 \text{ B}; Z_{ZT}<95 \text{ Om}$	SOD-123	K∙A
W5	BZT52C3V6	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 3.43.8 \text{ B}; Z_{ZT} \le 95 \text{ Om}$	SOD-123	K∙A
W5	BZT52C3V9S	DIODS	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 3.74.1 \text{ B}; Z_{ZT} < 900 \text{ m}$	SOD-323, SC-76	K•A





Код	Типономинал	Б	Φ	Особенности	Корпус	Ц:1•2
W5	BZX384B3V6	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 3.533.67 \text{ B}; Z_{ZT} < 90 \text{ Om}$	SOD-323, SC-76	K•A
W5	BZX384C3V6	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 3.43.8 \text{ B}; Z_{ZT} < 90 \text{ Om}$	SOD-323, SC-76	K • A
W6	BZT52B3V9	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 3.823.98 \text{ B}; Z_{ZT} < 95 \text{ Om}$	SOD-123	K • A
W6	BZT52C3V9	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA})=3.74.1 \text{ B}; Z_{ZT} < 95 \text{ Om}$	SOD-123	K • A
W6	BZT52C4V3S	DIODS	dz	$V_Z(I_{ZT}=5 \text{ mA})=44.6 \text{B}; Z_{ZT}<900 \text{m}$	SOD-323, SC-76	K • A
W6	BZX384B3V9	VISH	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 3.823.98 \text{ B}; Z_{ZT} < 90 \text{ Om}$	SOD-323, SC-76	K • A
W6	BZX384C3V9	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 3.74.1 \text{ B}; Z_{ZT} < 90 \text{ Om}$	SOD-323, SC-76	K ∙ A
W7	BZT52B4V3	VISH	dz	$V_2(I_{ZT} = 5 \text{ mA}) = 4.214.39 \text{ B}; Z_{ZT} < 95 \text{ Om}$	SOD-123	K•A
W7	BZT52C4V3	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA})=44.6 \text{B}; Z_{ZT}<950 \text{ m}$	SOD-123	K•A
W7	BZT52C4V7S	DIODS	dz	$V_Z(I_{ZT}=5 \text{ mA})=4.45B; Z_{ZT}<800 \text{ m}$	SOD-323, SC-76	K • A
W7	BZX384B4V3	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA})=4.214.39 \text{ B}; Z_{ZT}<90 \text{ Om}$	SOD-323, SC-76	K•A
W7	BZX384C4V3	VISH	dz	$V_2(I_{ZT} = 5 \text{ mA}) = 4.04.6 \text{ B}; Z_{ZT} < 90 \text{ Om}$	SOD-323, SC-76	K•A
W8	BZT52B4V7	VISH	dz	$V_2(I_{ZT} = 5 \text{ mA}) = 4.614.79 \text{ B}; Z_{ZT} < 80 \text{ Om}$	SOD-123	K•A
W8	BZT52C4V7	VISH	dz	$V_2(I_{ZT}=5 \text{ mA})=4.45B; Z_{ZT}<800 \text{ m}$	SOD-123	K•A
W8	BZT52C5V1S	DIODS	dz	$V_2(I_{ZT} = 5 \text{ mA}) = 4.85.4 \text{ B}; Z_{ZT} < 60 \text{ Om}$	SOD-323, SC-76	K•A
W8	BZX384B4V7	VISH	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 4.614.79 \text{ B}; Z_{ZT} < 80 \text{ Om}$	SOD-323, SC-76	K•A
W8	BZX384C4V7	VISH	dz	$V_2(I_{21}=5 \text{ mA})=4.45.0 \text{ B}, Z_{21}<80 \text{ Om}$	SOD-323, SC-76	K•A
W9	BZT52B5V1	VISH	dz	$V_2(I_{27} = 5 \text{ mA}) = 5.05.2 \text{ B}, Z_{27} < 60 \text{ Om}$	SOD-123	K•A
W9	BZT52C5V1	VISH	dz	$V_7(I_{77} = 5 \text{ mA}) = 4.85.4 \text{ B}; Z_{77} < 60 \text{ Om}$	SOD-123	K • A
W9	BZT52C5V6S	DIODS	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 5.26 \text{ B}; Z_{ZT} < 400 \text{ m}$	SOD-323, SC-76	K•A
W9	BZX384B5V1	VISH	dz	$V_z(I_{zz} = 5 \text{ mA}) = 5.05.2 \text{ B}; Z_{zz} < 60 \text{ Om}$	SOD-323, SC-76	K•A
W9	BZX384C5V1	VISH	dz	$V_2(I_{27} = 5 \text{ mA}) = 4.85.4 \text{ B}; Z_{27} < 60 \text{ Om}$	SOD-323, SC-76	K•A
WA	BZT52B5V6	VISH	dz	V ₂ (I ₂₇ = 5 mA) = 5.495.71 B; Z ₂₇ < 40 Om	SOD-123	K•A
WA	BZT52C5V6	VISH	dz	V _Z (I _{ZT} =5 mA)=5.26B; Z _{ZT} <40 Om	SOD-123	K•A
WA	BZT52C6V2S	DIODS	dz	V ₂ (I _{2T} = 5 mA) = 5.86.6B; Z _{2T} < 10 Om	SOD-323, SC-76	K•A
WA	BZX384B5V6	VISH	dz	V ₂ (I _{2T} = 5 mA) = 5.495.71 B; Z _{2T} < 40 Om	SOD-323, SC-76	K•A
WA	BZX384C5V6	VISH	dz	V _Z (I _{ZT} = 5 mA) = 5.26B; Z _{ZT} < 40 O m	SOD-323, SC-76	K•A
WA	SMZG3789A	GS	dz	V ₂ (I ₂ = 37.5 mA) = 10 B ± 10%; Z ₂₇ = 5.0 Om	DO-215AA	K•A
WB	BZT52B6V2	VISH	dz	V ₂ (I _{2T} = 5 mA) = 6.086.32 B; Z _{2T} < 10 Om	SOD-123	K • A
WB	BZT52C6V2	VISH	dz	V ₂ (I _{2T} = 5 mA) = 5.86.6B; Z _{2T} < 10 0 m	SOD-123	K•A
WB	BZT52C6V8S	DIODS	dz	V ₂ (I _{2T} = 5 mA) = 6.47.2B; Z _{2T} < 150m	SOD-323, SC-76	K•A
WB	BZX384B6V2	VISH	dz	V ₂ (I _{2T} = 5 mA) = 6.086.32 B; Z _{2T} < 10 Om	SOD-323, SC-76	K•A
WB	BZX384C6V2	VISH	dz	V ₇ (I ₂₇ = 5 mA) = 5.8 6.6B; Z ₂₇ < 10 Om	SOD-323, SC-76	K•A
WB	SMZG3789B	GS	dz	V ₂ (I ₂ =37.5 mA) = 10B±5%; Z ₂₇ =5.00m	DO-215AA	K•A
WC	BZT52B6V8	VISH	dz	V ₂ (I _{2T} = 5 mA) = 6.666.94 B; Z _{2T} < 8 Om	SOD-123	K•A
WC	BZT52C6V8	VISH	dz	V ₂ (I _{2T} = 5 mA) = 6.47.2B; Z _{2T} < 80m	SOD-123	K•A
WC	BZT52C7V5S	DIODS	dz	V ₂ (I _{2T} =5 mA) = 77.9B; Z _{2T} < 150m	SOD-323, SC-76	K•A
WC	BZX384B6V8	VISH	dz	V ₂ (I _{2T} =5 mA) = 6.666.94 B; Z _{2T} <15 Cm	SOD-323, SC-76	K•A
WC	BZX384C6V8	VISH	dz	V _Z (I _{ZT} = 5 mA) = 6.47.2 B; Z _{ZT} < 15 0 m	SOD-323, SC-76	K•A
WC	SMZG3790A	GS	dz	$V_2(I_2 = 34.1 \text{ mA}) = 11 \text{ B} \pm 10\%; Z_{27} = 6.0 \text{ Om}$	DO-215AA	K•A
WD	BZT52B7V5	VISH	dz	V ₂ (I _{2T} = 5 mA) = 7.357.65 B; Z _{2T} < 7 Om	SOD-123	K•A
WD	BZT52C7V5	VISH	dz	V ₂ (I _{2T} =5 mA)=77.9B; Z _{2T} <70m	SOD-123	K•A
WD	BZT52C8V2S	DIODS	dz	$V_2(I_{ZT} = 5 \text{ mA}) = 7.78.7 \text{ B}, Z_{ZT} < 70 \text{ M}$ $V_2(I_{ZT} = 5 \text{ mA}) = 7.78.7 \text{ B}; Z_{ZT} < 150 \text{ m}$	SOD-323, SC-76	K•A
WD	BZX384B7V5	VISH	dz	$V_2(I_{27} = 5 \text{ mA}) = 7.357.65 \text{ B}, Z_{27} \le 150 \text{ m}$	SOD-323, SC-76	K•A
WD	BZX384C7V5	VISH	dz	V _Z (I _{ZT} = 5 mA) = 77.5B; Z _{ZT} < 15 Om	SOD-323, SC-76	K•A
WD	SMZG3790B	GS	dz	$V_Z(I_{ZT} = 0 \text{ MA}) = 77.08; Z_{ZT} < 100 \text{M}$ $V_Z(I_Z = 34.1 \text{ MA}) = 11 \text{B} \pm 5\%; Z_{ZT} = 6.00 \text{M}$	DO-215AA	K•A
WE	BZT52B8V2	VISH	dz		SOD-123	K•A
WE	BZT52C8V2	VISH	dz	V _Z (I _{ZT} =5 mA) = 8.048.36 B; Z _{ZT} <70m	SOD-123 SOD-123	K•A
WE	BZ152C8V2 BZT52C9V1S	DIODS	cz cz	V ₂ (I _{2T} = 5 mA) = 7.78.7B; Z _{2T} < 70m	SOD-123 SOD-323, SC-76	K•A
WE		1/2010/06/06	1000	V ₂ (I _{ZT} = 5 mA) = 8.59.6B; Z _{ZT} < 15 Om		200
100000	BZX384B8V2	VISH	dz	V _z (I _{ZT} = 5 mA) = 8.048.36 B; Z _{ZT} < 15 Om	SOD-323, SC-76	K•A
WE	BZX384C8V2	VISH	dz	V _Z (I _{ZT} = 5 mA) = 7.78.7B; Z _{ZT} < 15 Om	SOD-323, SC-76	K•A
WE	SMZG3791A	GS	dz	$V_Z(I_Z=31.2 \text{ mA})=12 \text{ B} \pm 10\%; Z_{ZT}=7.0 \text{ Om}$	DO-215AA	K • A





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Код	Типономинал	Б	Ф	Особенности	Корпус	Ц:1•2
WF	BZT52B9V1	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 8.929.28 \text{ B}; Z_{ZT} \le 10 \text{ Om}$	SOD-123	K∙A
WF	BZT52C10S	DIODS	dz	$V_Z(I_{ZT}=5 \text{ mA}) = 9.410.6 \text{ B}; Z_{ZT} < 150 \text{ m}$	SOD-323, SC-76	K•A
WF	BZT52C9V1	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 8.59.6 \text{ B}; Z_{ZT} < 100 \text{ m}$	SOD-123	K•A
WF	BZX384B9V1	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 8.929.28 \text{ B}; Z_{ZT} < 15 \text{ Om}$	SOD-323, SC-76	K•A
WF	BZX384C9V1	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 8.59.6 \text{ B}; Z_{ZT} < 15 \text{ Om}$	SOD-323, SC-76	K•A
WF	SMZG3791B	GS	dz	$V_Z(I_Z=31.2 \text{ mA})=12 \text{ B} \pm 5\%; Z_{ZT}=7.0 \text{ Om}$	DO-215AA	K∙A
WG	BZT52B10	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA})=9.810.2 \text{ B}; Z_{ZT}<150 \text{ m}$	SOD-123	K•A
WG	BZT52C10	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA})=9.410.6 \text{ B}; Z_{ZT} < 150 \text{ m}$	SOD-123	K∙A
WG	BZT52C11S	DIODS	dz	$V_z(I_{zT} = 5 \text{ mA}) = 10.411.6 \text{ B}; Z_{zT} < 20 \text{ Om}$	SOD-323, SC-76	K∙A
WG	BZT52C12S	DIODS	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 11.412.7 \text{ B}; Z_{ZT} < 20 \text{ Om}$	SOD-323, SC-76	K•A
WG	BZT52C20S	DIODS	dz	$V_{z}(I_{zz} = 5 \text{ mA}) = 18.821.2 \text{ B}; Z_{zz} < 50 \text{ Om}$	SOD-323, SC-76	K∙A
WG	BZX384B10	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 9.810.2 \text{ B}; Z_{ZT} < 200 \text{ m}$	SOD-323, SC-76	K•A
WG	BZX384C10	VISH	dz	$V_Z(I_{Z1} = 5 \text{ mA}) = 9.410.6 \text{ B}; Z_{Z1} < 200 \text{ m}$	SOD-323, SC-76	K•A
WG	SMZG3792A	GS	dz	$V_z(I_z = 28.8 \text{ mA}) = 13\text{B} \pm 10\%; Z_{zz} = 7.5 \text{ Om}$	DO-215AA	K•A
WH	BZT52B11	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 10.811.2 \text{ B}; Z_{ZT} < 20 \text{ Om}$	SOD-123	K•A
WH	BZT52C11	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 10.411.6 \text{ B}; Z_{ZT} < 20 \text{ Om}$	SOD-123	K•A
WH	BZX384B11	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 10.811.2B; Z_{ZT} < 20.0 \text{m}$	SOD-323, SC-76	K•A
WH	BZX384C11	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 10.411.6B; Z_{ZT} < 20 \text{ Om}$	SOD-323, SC-76	K•A
WH	SMZG3792B	GS	dz	V _z (I _z =28.8 mA)=13 B±5%; Z _{zz} =7.5 Om	DO-215AA	K•A
WI	BZT52B12	VISH	dz	V _Z (I _{ZT} = 5 mA) = 11.812.2B; Z _{ZT} < 20 Om	SOD-123	K•A
WI	BZT52C12	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 11.412.7B, Z_{ZT} < 20 \text{ Om}$	SOD-123	K•A
WI	BZT52C13S	DIODS	dz	$V_Z(I_{ZI} = 5 \text{ mA}) = 12.414.1 \text{ B}; Z_{ZI} < 25 \text{ Om}$	SOD-323, SC-76	K•A
WI	BZX384B12	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 11.812.2 \text{ B}; Z_{ZT} < 25 \text{ Om}$	SOD-323, SC-76	K•A
WI	BZX384C12	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 11.412.7 \text{ B; } Z_{ZT} < 25 \text{ Om}$	SOD-323, SC-76	K•A
WI	SMZG3793A	GS	dz	V _Z (I _Z =25.0 mA) = 15B ± 10%; Z _{ZT} =9.00m	DO-215AA	K•A
WJ	BZT52C15S	DIODS	dz	$V_Z(I_{ZI}=5 \text{ MA})=13.815.6 \text{ B; } Z_{ZI}<30 \text{ OM}$	SOD-323, SC-76	K•A
W.J	SMZG3793B	GS	dz	V _Z (I _Z =25.0 mA)=15.8 ±5%; Z _Z T=9.0 Om	DO-215AA	K•A
WK	BZT52B13	VISH	dz	$V_Z(I_{ZI}=5 \text{ MA})=12.713.3 \text{ B; } Z_{ZI}<25.0 \text{ M}$	SOD-123	K•A
WK	BZT52C13	VISH	dz	$V_Z(I_{ZI} = 5 \text{ MA}) = 12.414.1 \text{ B}; Z_{ZI} < 25 \text{ OM}$	SOD-123	K•A
WK	BZT52C16S	DIODS	dz	$V_Z(I_{ZI} = 5 \text{ MA}) = 15.317.1 \text{ B}; Z_{ZI} < 40 \text{ OM}$	SOD-323, SC-76	K•A
WK	BZX384B13	VISH	dz	$V_Z(I_{ZI} = 5 \text{ MA}) = 12.713.3 \text{ B; } Z_{ZI} < 30 \text{ OM}$	SOD-323, SC-76	K•A
WK	BZX384C13	VISH	dz	$V_z(I_{ZI} = 5 \text{ MA}) = 12.414.1 \text{ B; } Z_{ZI} < 30 \text{ OM}$	SOD-323, SC-76	K•A
WK	SMZG3794A	GS	dz	V _Z (I _{ZT} = 3.4 mA) = 16B ± 10%; Z _{ZT} = 10.0 Cm	DO-215AA	K•A
WL	BZT52B15	VISH	200	$V_z(I_{zz}=5 \text{ MA})=14.715.3 \text{ B; } Z_{zz}<30 \text{ OM}$	SOD-123	K•A
WL	100	VISH	dz	212)		K•A
WL	BZT52C15 BZT52C18S	DIODS	dz	V _Z (I _{ZT} =5 mA) = 13.815.6B; Z _{ZT} < 30 Om	SOD-123	
		VISH	dz	V _Z (I _{ZT} =5 mA) =16.819.1B; Z _{ZT} <50 Om	SOD-323, SC-76	K●A
WL WL	BZX384B15	VISH	dz	V _Z (I _{ZT} =5 mA) =14.715.3B; Z _{ZT} <30 Om	SOD-323, SC-76 SOD-323, SC-76	K•A
WL	BZX384C15		dz	V _Z (I _{ZT} =5 MA) = 13.815.6B; Z _{ZT} < 30 OM		K•A
5000	SMZG3794B	GS	dz	V _Z (I _Z =23.4 mA) = 16 B ±5%; Z _{ZT} = 10.0 Cm	DO-215AA	K•A
WM	BZT52B16	VISH	dz	V _Z (I _{ZT} =5 mA) =15.716.3B; Z _{ZT} <40 0m	SOD-123	K•A
WM	BZT52C16	VISH	dz	V _Z (I _{ZT} =5 mA) = 15.317.1B; Z _{ZT} <40 0m	SOD-123	K•A
WM	BZX384B16	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 15.716.3 \text{ B}; Z_{ZT} < 40 \text{ Om}$	SOD-323, SC-76	K●A
WM	BZX384C16	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 15.317.1 \text{ B}; Z_{ZT} < 40 \text{ Om}$	SOD-323, SC-76	K•A
WN	BZT52B18	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 17.618.4 \text{ B}; Z_{ZT} < 50 \text{ Om}$	SOD-123	K∙A
WN	BZT52C18	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 16.819.1 \text{ B}; Z_{ZT} < 50 \text{ Om}$	SOD-123	K∙A
WN	BZT52C22S	DIODS	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 21.622.4 \text{ B}; Z_{ZT} < 55 \text{ Om}$	SOD-323, SC-76	K∙A
WN	BZX384B18	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 17.618.4 \text{ B}; Z_{ZT} < 45 \text{ Om}$	SOD-323, SC-76	K◆A
WN	BZX384C18	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 16.819.1 \text{ B}; Z_{ZT} < 45 \text{ Om}$	SOD-323, SC-76	K∙A
WO	BZT52B20	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 19.620.4 \text{ B}; Z_{ZT} < 50 \text{ Om}$	SOD-123	K∙A
WO	BZT52C20	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 18.821.2 \text{ B}; Z_{ZT} < 50 \text{ Om}$	SOD-123	K∙A
WO	BZT52C24S	DIODS	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 22.823.3 \text{ B}; Z_{ZT} < 80 \text{ Om}$	SOD-323, SC-76	K∙A
WO	BZX384B20	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 19.620.4 \text{ B}; Z_{ZT} < 55 \text{ Om}$	SOD-323, SC-76	K•A

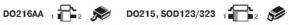




Код	Типономинал	6	Φ	Особенности	Корпус	Ц:1•2
WO	BZX384C20	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 18.821.2 \text{ B}; Z_{ZT} < 55 \text{ Om}$	SOD-323, SC-76	K•A
WP	BZT52B22	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 21.622.4 \text{ B}; Z_{ZT} < 55 \text{ Om}$	SOD-123	K • A
WP	BZT52C22	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 21.622.4 \text{ B; } Z_{ZT} < 55 \text{ Om}$	SOD-123	K • A
WP	BZT52C27S	DIODS	dz	$V_Z(I_{ZT}=2mA)=25.128.9 B; Z_{ZT} < 80 Om$	SOD-323, SC-76	K • A
WP	BZX384B22	VISH	dz	V _Z (I _{ZT} = 5 mA) = 21.622.4 B; Z _{ZT} < 55 Om	SOD-323, SC-76	K • A
WP	BZX384C22	VISH	dz	V _Z (I _{ZT} = 5 mA) = 20.823.3 B; Z _{ZT} < 55 Om	SOD-323, SC-76	K • A
WQ	BZT52C30S	DIODS	dz	$V_Z(I_{ZT} = 2 \text{ mA}) = 2832 \text{ B}; Z_{ZT} < 80 \text{ Om}$	SOD-323, SC-76	K ∙ A
WR	BZT52B24	VISH	dz	V _Z (I _{ZT} = 5 mA) = 23.524.5 B; Z _{ZT} < 80 Om	SOD-123	K • A
WR	BZT52C24	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA}) = 22.823.3 \text{ B; } Z_{ZT} < 80 \text{ Om}$	SOD-123	K●A
WR	BZT52C33S	DIODS	dz	$V_Z(I_{ZT}=2 \text{ mA}) = 3135 \text{ B}; Z_{ZT} < 80 \text{ Om}$	SOD-323, SC-76	K • A
WR	BZX384B24	VISH	dz	V _Z (I _{ZT} = 5 mA) = 23.524.5 B; Z _{ZT} < 70 Om	SOD-323, SC-76	K • A
WR	BZX384C24	VISH	dz	$V_2(I_{2T} = 5 \text{ mA}) = 22.825.6 \text{ B; } Z_{2T} < 70 \text{ Om}$	SOD-323, SC-76	K • A
WS	BZT52B27	VISH	dz	V ₂ (I ₇₇ =5mA)=26.527.5 B; Z ₇₇ <80 Om	SOD-123	K ∙ A
₩S	BZT52C27	VISH	dz	V ₂ (I ₇₇ =5mA)=25.128.9 B; Z ₇₇ <80 Om	SOD-123	K • A
WS	BZT52C36S	DIODS	dz	$V_2(I_{2T}=2 \text{ mA}) = 3438 \text{ B}; Z_{2T} < 90 \text{ Om}$	SOD-323, SC-76	K•A
WS	BZX384B27	VISH	dz	V _Z (I _{ZT} = 2mA) = 26.527.5 B; Z _{ZT} < 80 Om	SOD-323, SC-76	K•A
WS	BZX384C27	VISH	dz	$V_2(I_{2T} = 2 \text{ mA}) = 25.128.9 \text{ B}; Z_{2T} < 80 \text{ Om}$	SOD-323, SC-76	K•A
WT	BZT52B30	VISH	dz	$V_2(I_{27}=5 \text{ mA}) = 29.430.6 \text{ B}; Z_{27} < 80 \text{ Om}$	SOD-123	K•A
WT	BZT52C30	VISH	dz	V ₂ (I _{2T} = 5 mA) = 2832 B; Z _{2T} < 80 Om	SOD-123	K•A
WT	BZT52C39S	DIODS	dz	V _Z (I _{ZT} = 2 mA) = 3741B; Z _{ZT} < 130 Om	SOD-323, SC-76	K•A
WT	BZX384B30	VISH	dz	V _z (I _{zz} = 2 mA) = 29.430.6 B; Z _{zz} < 80 Om	SOD-323, SC-76	K•A
WT	BZX384C30	VISH	dz	V _Z (I _{ZT} = 2 mA) = 2832B; Z _{ZT} < 80 Om	SOD-323, SC-76	K•A
WU	BZT52B33	VISH	dz	V ₂ (I ₂₇ = 5 mA) = 32.333.7 B; Z ₂₇ < 80 Om	SOD-123	K•A
WU	BZT52C33	VISH	dz	V ₂ (I _{ZT} = 5 mA) = 3135B; Z _{ZT} < 80 Om	SOD-123	K•A
WU	BZX384B33	VISH	dz	V ₂ (I _{2T} = 2 mA) = 32.333.7 B; Z _{2T} < 80 Om	SOD-323, SC-76	K•A
WU	BZX384C33	VISH	dz	V ₂ (I _{ZT} = 2 mA) = 3135B; Z _{ZT} < 80 Om	SOD-323, SC-76	K • A
ww	BZT52B36	VISH	dz	V ₂ (I _{2T} = 5 mA) = 35.336.7 B; Z _{2T} < 90 Om	SOD-123	K•A
WW	BZT52C36	VISH	dz	V ₂ (I ₂₇ = 5 mA) = 3438 B; Z ₂₇ < 90 Om	SOD-123	K•A
WW	BZX384B36	VISH	dz	V ₂ (I _{2T} = 2 mA) = 35.336.7 B; Z _{2T} < 90 Om	SOD-323, SC-76	K•A
WW	BZX384C36	VISH	dz	V ₂ (I _{2T} = 2 mA) = 3438 B; Z _{2T} < 90 Om	SOD-323, SC-76	K•A
WX	BZT52B39	VISH	dz	V ₂ (I _{2T} = 5 mA) = 38.239.8 B; Z _{2T} < 90 Om	SOD-123	K•A
WX	BZT52C2V4S	DIODS	dz	V ₂ (I _{2T} = 5 mA) = 2.22.6B; Z _{2T} < 100 Om	SOD-323, SC-76	K•A
WX	BZT52C39	VISH	dz	V ₂ (I _{2T} = 5 mA) = 3741B; Z _{2T} < 90 Om	SOD-123	K•A
WX	BZX384B39	VISH	dz	V ₂ (I _{2T} = 2 mA) = 38.239.8 B; Z _{2T} < 130 Om	SOD-323, SC-76	K•A
WX	BZX384C39	VISH	dz	V ₂ (I _{2T} = 2 mA) = 3741 B; Z _{2T} < 130 Om	SOD-323, SC-76	K•A
WY	BZT52B43	VISH	dz	V ₂ (I _{2T} = 5 mA) = 42.143.9 B; Z _{2T} < 100 Om	SOD-123	K•A
WY	BZT52C2V0S	DIODS	dz	$V_2(I_{ZT} = 5 \text{ MA}) = 42.143.9 \text{ B, } Z_{ZT} < 100 \text{ G/m}$ $V_2(I_{ZT} = 5 \text{ MA}) = 1.912.09 \text{ B; } Z_{ZT} < 100 \text{ G/m}$	SOD-323, SC-76	K•A
WY	BZT52C2V03	VISH	dz	$V_2(I_{ZT} = 5 \text{ MA}) = 1.912.09 \text{ B, } Z_{ZT} < 100 \text{ GM}$ $V_2(I_{ZT} = 5 \text{ MA}) = 4046 \text{ B; } Z_{ZT} < 100 \text{ GM}$	SOD-123	K•A
WY	BZX384B43	VISH	dz	$V_2(I_{ZT} = SMA) = 4048B, Z_{ZT} < 150 OM$ $V_2(I_{ZT} = 2 MA) = 42.143.9 B; Z_{ZT} < 150 OM$	SOD-323, SC-76	K•A
WY	BZX384C43	VISH	dz	$V_Z(I_{ZT} = 2 \text{ MA}) = 42.143.9 \text{ B}, Z_{ZT} < 130 \text{ GM}$ $V_Z(I_{ZT} = 2 \text{ MA}) = 4046 \text{ B}; Z_{ZT} < 130 \text{ GM}$	SOD-323, SC-76	K•A
WZ	BZT52B47	VISH	dz	$V_2(I_{ZT} = 5 \text{ MA}) = 4040 \text{ B, } Z_{ZT} < 130 \text{ G/m}$ $V_2(I_{ZT} = 5 \text{ MA}) = 46.147.9 \text{ B; } Z_{ZT} < 100 \text{ G/m}$	SOD-123	K•A
WZ	BZ152B47 BZT52C47	VISH	dz		SOD-123	K•A
WZ	BZX384B47	VISH		V _Z (I _{ZT} = 5 mA) = 4450B; Z _{ZT} < 100 Om	SOD-323, SC-76	K•A
WZ	BZX384B47 BZX384C47	VISH	dz	V _z (I _{zT} = 2 mA) = 46.147.9 B; Z _{zT} < 170 Om	SOD-323, SC-76	K•A
60000	1000200000000000	100000000000000000000000000000000000000	dz	V _Z (I _{ZT} = 2 mA) = 4450B; Z _{ZT} < 150 Om	The state of the Arrange of the	0.00
Х (бел)	BB833	INF	var	V _R <30 B; I _F <20 мA; I _R <0.02 мкА; С _{1B} =8.510 пФ; С _{2BB} =0.60.9	SOD-323, SC-76	K•A
Х (жел)	BB835	INF	var	V _R <30 B; I _F <20мA; I _R <0.02мкA; С _{1B} =8.510 пФ; С _{28B} =0.50.75	SOD-323, SC-76	K•A
X1	BZT52B51	VISH	dz	V _Z (I _{ZT} = 5 mA) = 50.052.0 B; Z _{ZT} < 100 Om	SOD-123	K•A
X1	BZT52C51	VISH	dz	V _Z (I _{ZT} = 5 mA) = 4854B; Z _{ZT} < 100 Om	SOD-123	K•A
X1	BZX384B51	VISH	dz	$V_2(I_{ZT} = 2 \text{ mA}) = 50.052.0 \text{ B}; Z_{ZT} < 180 \text{ Om}$	SOD-323, SC-76	K • A
X1	BZX384C51	VISH	dz	$V_Z(I_{ZT} = 2 \text{ mA}) = 4854 \text{ B}; Z_{ZT} < 180 \text{ Om}$	SOD-323, SC-76	K•A
X1	CMDZ5221B	CSI	dz	V ₂ =2.4B(5%); P _D <250mBT	SOD-323, SC-76	K•A
X 1	MMSZ16T1	ON	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 15.216.8 \text{ B}; I_R < 0.05 \text{ mkA}$	SOD-123	K • A









Код	Типономинал	Б	Ф	Особенности	Корпус	Ц:1•2
Х2	BZT52B56	VISH	dz	$V_Z(I_{ZT}=2.5 \text{ mA}) = 54.957.1 \text{B}; Z_{ZT} < 135 \text{ Om}$	SOD-123	K∙A
Х2	BZT52C56	VISH	dz	V _Z (I _{ZT} = 2.5 mA) = 5260 B; Z _{ZT} < 135 Om	SOD-123	K∙A
Х2	BZX384B56	VISH	dz	$V_Z(I_{ZT}=2 \text{ mA}) = 54.957.1 \text{ B}; Z_{ZT} < 200 \text{ Om}$	SOD-323, SC-76	K•A
X2	BZX384C56	VISH	dz	V _Z (I _{ZT} = 2 mA) = 5260 B; Z _{ZT} < 200 Om	SOD-323, SC-76	K∙A
Х2	CMDZ5222B	CSI	dz	V _Z =2.5B(5%); P _D <250 mBt	SOD-323, SC-76	K•A
Х2	MMSZ18T1	ON	dz	V _Z (I _{ZT} =5 mA) = 17.118.9B; I _B < 0.05 mkA	SOD-123	K•A
ХЗ	BZT52B62	VISH	dz	$V_Z(I_{ZT} = 2.5 \text{ mA}) = 60.863.2 \text{ B}; Z_{ZT} < 135 \text{ Om}$	SOD-123	K•A
ХЗ	BZT52C62	VISH	dz	V _Z (I _{ZT} = 2.5 mA) = 5866 B; Z _{ZT} < 135 Om	SOD-123	K∙A
Х3	BZX384B62	VISH	dz	$V_Z(I_{ZT}=2 \text{ mA}) = 60.863.2 \text{B}; Z_{ZT} \le 215 \text{ Om}$	SOD-323, SC-76	K∙A
ХЗ	BZX384C62	VISH	dz	V _Z (I _{ZT} = 2 mA) = 5866B; Z _{ZT} < 215 Om	SOD-323, SC-76	K∙A
ХЗ	CMDZ5223B	CSI	dz	V _Z =2.7B(5%); P _D <250 мВт	SOD-323, SC-76	K◆A
ХЗ	MMSZ20T1	ON	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 19.021.0 \text{ B}; I_{S} < 0.05 \text{ mkA}$	SOD-123	K•A
Х4	BZT52B68	VISH	dz	$V_Z(I_{ZT} = 2.5 \text{ mA}) = 66.669.4 \text{B}; Z_{ZT} < 200 \text{ Om}$	SOD-123	K•A
Х4	BZT52C68	VISH	dz	$V_Z(I_{ZT} = 2.5 \text{ mA}) = 6472 \text{ B}; Z_{ZT} < 200 \text{ Om}$	SOD-123	K•A
Х4	BZX384B68	VISH	dz	V _Z (I _{ZT} = 2 mA) = 66.669.4 B; Z _{ZT} < 240 Om	SOD-323, SC-76	K•A
Х4	BZX384C68	VISH	dz	V _Z (I _{ZT} = 2 mA) = 6472B; Z _{ZT} < 240 Om	SOD-323, SC-76	K◆A
Х4	CMDZ5224B	CSI	dz	Vz=2.8B(5%); Po<250mBr	SOD-323, SC-76	K•A
Х4	MMSZ22T1	ON	dz	$V_7(I_{77}=5 \text{ mA}) = 20.923.1 \text{ B}; I_8 < 0.05 \text{ mkA}$	SOD-123	K∙A
X5	BZT52B75	VISH	dz	$V_7(I_{77} = 2.5 \text{ mA}) = 73.576.5 \text{ B}; Z_{77} < 250 \text{ Om}$	SOD-123	K•A
X5	BZT52C75	VISH	dz	$V_Z(I_{ZI} = 2.5 \text{ mA}) = 7079 \text{B}; Z_{ZI} < 250 \text{ Om}$	SOD-123	K•A
X5	BZX384B75	VISH	dz	V _Z (I _{ZT} = 2 mA) = 73.576.5 B; Z _{ZT} < 255 Om	SOD-323, SC-76	K•A
Х5	BZX384C75	VISH	dz	$V_Z(I_{ZT} = 2 \text{ mA}) = 7079 \text{ B}; Z_{ZT} < 255 \text{ Om}$	SOD-323, SC-76	K•A
Х5	CMDZ5225B	CSI	dz	Vz=3.0B(5%); Pp<250mBt	SOD-323, SC-76	K•A
X5	MMSZ24T1	ON	dz	V _Z (I _{Z1} =5 mA) = 22.825.2B; I _B < 0.05 mkA	SOD-123	K∙A
X6	CMDZ5226B	CSI	dz	V ₂ =3.3B (5%); P _D <250mBt	SOD-323, SC-76	K∙A
Χ7	CMDZ5227B	CSI	dz	V _Z =3.6B(5%); P _D <250 mBr	SOD-323, SC-76	K∙A
Х8	CMDZ5228B	CSI	dz	V ₂ =3.9B(5%); P ₀ <250mBr	SOD-323, SC-76	K•A
Х9	CMDZ5229B	CSI	dz	Vz=4.3B(5%); Po<250mBt	SOD-323, SC-76	K•A
XΑ	CMDZ5230B	CSI	dz	Vz=4.7B(5%); Pp<250mBt	SOD-323, SC-76	K•A
XΑ	SMZG3795A	GS	dz	$V_Z(I_Z = 20.8 \text{ mA}) = 18\text{B} \pm 10\%; Z_{ZT} = 12.0 \text{ Om}$	DO-215AA	K•A
ΧВ	CMDZ5231B	CSI	dz	V _Z =5.1B(5%); P _D <250 mBr	SOD-323, SC-76	K∙A
ХВ	SMZG3795B	GS	dz	V _Z (I _Z =20.8 mA)=18 B ±5%; Z _{ZT} =12.0 Om	DO-215AA	K∙A
XC	CMDZ5232B	CSI	dz	V _Z =5.6B(5%); P _D <250mBt	SOD-323, SC-76	K•A
XC	SMZG3796A	GS	dz	$V_Z(I_Z = 18.7 \text{ mA}) = 20 \text{B} \pm 10\%; Z_{ZT} = 14.0 \text{ Om}$	DO-215AA	K∙A
XD	CMDZ5233B	CSI	dz	Vz=6.0B(5%); Po<250mBr	SOD-323, SC-76	K∙A
XD	SMZG3796B	GS	dz	$V_Z(I_Z = 18.7 \text{ mA}) = 20 \text{ B} \pm 5\%; Z_{ZT} = 14.0 \text{ Om}$	DO-215AA	K•A
XE	CMDZ5234B	CSI	dz	V _Z =6.2 B (5%); P _D <250 mBt	SOD-323, SC-76	K∙A
XE	SMZG3797A	GS	dz	$V_Z(I_Z = 17.0 \text{ mA}) = 22 \text{B} \pm 10\%; Z_{ZT} = 17.5 \text{ Om}$	DO-215AA	K•A
XF	CMDZ5235B	CSI	dz	V _Z =6.8 B (5%); P _D <250 mBt	SOD-323, SC-76	K•A
XF	SMZG3797B	GS	dz	V _Z (I _Z =17.0 mA)=22 B ±5%; Z _{ZT} =17.5 Om	DO-215AA	K•A
XG	CMDZ5236B	CSI	dz	Vz=7.5B(5%); Pp<250mBt	SOD-323, SC-76	K∙A
XG	SMZG3798A	GS	dz	$V_Z(I_Z = 15.6 \text{ mA}) = 24 \text{B} \pm 10\%; Z_{ZT} = 19.0 \text{ Om}$	DO-215AA	K•A
ХН	CMDZ5237B	CSI	dz	V _Z =8.2 B (5%); P _D <250 mBt	SOD-323, SC-76	K•A
ХН	MMSD701T1	ON	shd	$V_R < 70B$; $V_F (I_F = 10 \text{ mA}) < 1B$; $C_D < 1 \text{ n}\Phi$	SOD-123	K∙A
ХН	SMZG3798B	GS	dz	$V_Z(I_Z=15.6 \text{ mA})=24 \text{ B} \pm 5\%; Z_{ZT}=19.0 \text{ Om}$	DO-215AA	K∙A
XI	SMZG3799A	GS	dz	$V_Z(I_Z = 13.9 \text{ mA}) = 27 \text{ B} \pm 10\%; Z_{ZT} = 23.0 \text{ Om}$	DO-215AA	K∙A
XJ	CMDZ5238B	CSI	dz	V _Z =8.7B(5%); P _D <250mBt	SOD-323, SC-76	K◆A
X.J	SMZG3799B	GS	dz	V _Z (I _Z =13.9 mA)=27 B±5%; Z _{ZT} =23.0 Om	DO-215AA	K∙A
XK	CMDZ5239B	CSI	dz	V _Z =9.1B(5%); P _D <250 mBr	SOD-323, SC-76	K•A
XK	SMZG3800A	GS	dz	V _Z (I _Z =12.5 mA)=30B±10%; Z _{ZT} =26.0 Om	DO-215AA	K•A
XL	CMDZ5240B	CSI	dz	V _Z = 10 B (5%); P ₀ < 250 mBT	SOD-323, SC-76	K•A
XL	SMZG3800B	GS	dz	V _Z (I _Z = 12.5 mA) = 30 B ±5%; Z _{ZT} = 26.0 Om	DO-215AA	K•A





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц:1•2
XN	CMDZ5241B	CSI	dz	$V_2 = 11 B(5\%); P_0 < 250 MBT$	SOD-323, SC-76	K∙A
XO	CMDZ5242B	CSI	dz	$V_z = 12 B(5\%); P_D < 250 MBT$	SOD-323, SC-76	K∙A
XP	CMDZ13L	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 13 \text{ B; } P_D < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
XP	CMDZ5243B	CSI	dz	$V_Z = 13 B(5\%); P_D < 250 MBT$	SOD-323, SC-76	K∙A
XQ	CMDZ5244B	CSI	dz	$V_Z = 14 B (5\%); P_D < 250 MBT$	SOD-323, SC-76	K∙A
XR	CMDZ5245B	CSI	dz	$V_z = 15 B(5\%); P_D < 250 MBT$	SOD-323, SC-76	K●A
XS	CMDZ5246B	CSI	dz	$V_z = 16 B (5\%); P_0 < 250 MBT$	SOD-323, SC-76	K∙A
XT	CMDZ5247B	CSI	dz	$V_2 = 17 B(5\%); P_0 < 250 MBT$	SOD-323, SC-76	K•A
XT	MMSD301T1	ON	shd	$V_R < 30 \text{ B}; V_F (I_F = 10 \text{ mA}) < 0.6 \text{ B}; C_D < 1.5 \text{ n}\Phi$	SOD-123	K•A
XU	CMDZ5248B	CSI	dz	V _Z = 18 B (5%); P _D < 250 mBT	SOD-323, SC-76	K•A
ΧV	CMDZ5249B	CSI	dz	$V_z = 19B(5\%); P_D < 250 MBT$	SOD-323, SC-76	K•A
XX	CMDZ5250B	CSI	dz	$V_Z = 20 B(5\%); P_O < 250 MBT$	SOD-323, SC-76	K•A
XY	CMDZ5251B	CSI	dz	Vz=22B(5%); Po<250mBT	SOD-323, SC-76	K∙A
XZ	CMDZ5252B	CSI	dz	Vz = 24 B (5%); Po < 250 mBT	SOD-323, SC-76	K•A
Y1	CMDZ5253B	CSI	dz	Vz = 25 B (5%); Po < 250 mBT	SOD-323, SC-76	K•A
Y1	MMSZ27T1	ON	dz	V _Z (I _{ZT} = 5 mA) = 25.6528.35 B; I _B < 0.05 mkA	SOD-123	K•A
Y2	CMDZ5254B	CSI	dz	Vz = 27 B (5%); Po < 250 mBT	SOD-323, SC-76	K•A
Y2	MMSZ30T1	ON	dz	V ₂ (I _{2T} = 5 mA) = 28.5031.5 B; I _B < 0.05 mkA	SOD-123	K•A
Y3	CMDZ5255B	CSI	dz	V ₂ =28B(5%); P _D <250mBT	SOD-323, SC-76	K∙A
Y3	MMSZ33T1	ON	dz	V ₂ (I ₂₁ = 5 mA) = 31.3534.65 B; I _B < 0.05 mkA	SOD-123	K•A
Y4	CMDZ5256B	CSI	dz	V ₂ =30B(5%); P _D <250mB _T	SOD-323, SC-76	K•A
Y4	MMSZ36T1	ON	dz	V _Z (I _{ZT} = 5 mA) = 34.237.8 B; I _B < 0.05 mrA	SOD-123	K•A
Y5	CMDZ5257B	CSI	dz	V ₂ =33B(5%); P _D <250mB _T	SOD-323, SC-76	K•A
Y5	MMSZ39T1	ON	dz	V ₂ (I _{ZT} = 5 mA) = 37.0541.0 B; I _B < 0.05 mrA	SOD-123	K•A
Y6	CMDZ5258B	CSI	dz	V ₂ =36B(5%); P ₀ <250 мВт	SOD-323, SC-76	K•A
Y7	CMDZ5259B	CSI	dz	V _z = 39 B (5%); P _D < 250 MBT	SOD-323, SC-76	K•A
Y8	CMDZ5260B	CSI	dz	V ₂ =43 B(5%); P ₀ <250 MBT	SOD-323, SC-76	K•A
Y9	CMDZ5261B	CSI	dz	V ₇ =47B(5%); P _D <250mB _T	SOD-323, SC-76	K•A
YA	SMZG3801A	GS	dz	$V_2(I_2 = 11.4 \text{ mA}) = 33 \text{ B} \pm 10\%; Z_{2T} = 33.0 \text{ Om}$	DO-215AA	K•A
YB	SMZG3801B	GS	dz	$V_2(I_2 = 11.4 \text{ mA}) = 33 \text{ B} \pm 5\%; Z_{21} = 33.0 \text{ Om}$	DO-215AA	K•A
YC	SMZG3802A	GS	dz	V ₂ (I ₂ = 10.4 mA) = 36 B ± 10%; Z _{2T} = 38.0 Om	DO-215AA	K•A
YD	SMZG3802B	GS	dz	$V_2(I_2 = 10.4 \text{ mA}) = 36 \text{B} \pm 5\%; Z_{27} = 38.0 \text{ Om}$	DO-215AA	K•A
YE	SMZG3803A	GS	dz	$V_7 (I_7 = 9.6 \text{ mA}) = 39 \text{B} \pm 10\%; Z_{77} = 45.0 \text{ OM}$	DO-215AA	K•A
YF	SMZG3803B	GS	dz	V _Z (I _Z =9.6 mA)=39B±5%; Z _{ZT} =45.00m	DO-215AA	K•A
YG	SMZG3804A	GS	dz	$V_2(I_2 = 8.7 \text{ mA}) = 43 \text{B} \pm 10\%; Z_{21} = 53.0 \text{ Om}$	DO-215AA	K•A
YH	SMZG3804B	GS	dz	$V_2(I_2 = 8.7 \text{ mA}) = 43 \text{ B} \pm 5\%; Z_{21} = 53.0 \text{ Om}$	DO-215AA	K∙A
ΥI	SMZG3805A	GS	dz	$V_2(I_2 = 8.0 \text{ mA}) = 47 \text{B} \pm 10\%; Z_{22} = 67.0 \text{ Om}$	DO-215AA	K∙A
YJ	SMZG3805B	GS	dz	$V_z(I_z = 8.0 \text{ mA}) = 47 \text{B} \pm 5\%; Z_{zz} = 67.00 \text{m}$	DO-215AA	K•A
YK	SMZG3806A	GS	dz	$V_z(I_z = 7.3 \text{ mA}) = 51 \text{ B} \pm 10\%; Z_{zz} = 70.0 \text{ Om}$	DO-215AA	K•A
YL	SMZG3806B	GS	dz	$V_2(I_2 = 7.3 \text{ mA}) = 51 \text{ B} \pm 5\%; Z_{21} = 70.00 \text{ m}$	DO-215AA	K•A
YP	CMDZ15L	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 15 \text{ B}; P_D < 250 \text{ mB}T$	SOD-323, SC-76	K•A
Z0	PDZ2.4B	PHIL	dz	$V_z = 2.4 \text{ B; } Z_{zt} (I_z = 5 \text{ mA}) = 100 \text{ Om}$	SOD-323, SC-76	K∙A
Z1	MMSZ43T1	ON	dz	$V_2(I_{TT}=5 \text{ mA})=40.8545.15 \text{ B}; I_B < 0.05 \text{ mKA}$	SOD-123	K•A
Z1	PDZ2.7B	PHIL	dz	$V_2 = 2.7 \text{ B}; Z_{ZI} (I_2 = 5 \text{ mA}) = 100 \text{ Om}$	SOD-323, SC-76	K•A
Z2	MMSZ47T1	ON	dz	V _Z (I _{ZT} = 5 mA) = 44.6549.35 B; I _B < 0.05 mkA	SOD-123	K∙A
Z2	PDZ3.0B	PHIL	dz	V ₂ =3.0 B; Z _{ZT} (I ₂ =5 mA) = 95 Om	SOD-323, SC-76	K∙A
Z3	MMSZ51T1	ON	dz	$V_Z(I_{Z1} = 5 \text{ mA}) = 48.4553.55 \text{ B}; I_B < 0.05 \text{ mKA}$	SOD-123	K∙A
Z3	PDZ3.3B	PHIL	dz	V _z =3.3 B; Z _{zt} (I _z =5 mA) = 95 Om	SOD-323, SC-76	K•A
Z4	MMSZ56T1	ON	dz	V ₂ (I _{ZT} = 5 mA) = 53.2058.80 B; I _B < 0.05 mkA	SOD-123	K•A
Z4	PDZ3.6B	PHIL	dz	V _z =3.6 B; Z _{ZT} (I _z =5 mA) = 90 Om	SOD-323, SC-76	K∙A
Z5	MMSZ62T1	ON	dz	V ₂ (I _{ZT} = 5 mA) = 57.0063.00 B; I _B < 0.05 mkA	SOD-123	K•A
Z5	PDZ3.9B	PHIL	dz	V _z = 3.9 B; Z _{ZT} (I _z = 5 mA) = 90 Om	SOD-323, SC-76	K•A





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Код	Типономинал	6	Ф	Особенности	Корпус	Ц:1•2
Z6	MMSZ68T1	ON	dz	$V_Z(I_{ZT}=5 \text{ mA}) = 64.6071.40 \text{ B}; I_R < 0.05 \text{ mKA}$	SOD-123	K∙A
Z6	PDZ4.3B	PHIL	dz	V _Z =4.3 B; Z _{ZT} (I _Z =5 mA) = 90 Om	SOD-323, SC-76	K◆A
Z7	MMSZ75T1	ON	dz	V _Z (I _{ZT} =5 mA) =71.2578.75 B; I _R < 0.05 mkA	SOD-123	K•A
Z7	PDZ4.7B	PHIL	dz	Vz=4.7B; ZzT (Iz=5mA)=90 Om	SOD-323, SC-76	K∙A
Z8	PDZ5.1B	PHIL	dz	Vz=5.1B; ZzT (Iz=5mA)=60 Om	SOD-323, SC-76	K•A
Z9	PDZ5.6B	PHIL	dz	V _Z =5.6B; Z _{ZT} (I _Z =5mA)=50 Om	SOD-323, SC-76	K•A
ZA	PDZ6.2B	PHIL	dz	V _Z =6.2 B; Z _{ZT} (I _Z =5 mA) = 50 Om	SOD-323, SC-76	K•A
ZA	SMZG3807A	GS	dz	V _Z (I _Z =6.7mA)=56 B±10%; Z _{ZT} =86.0 Om	DO-215AA	K•A
ZB	PDZ6.8B	PHIL	dz	V _Z =6.8 B; Z _{ZT} (I _Z =5mA)=40 Om	SOD-323, SC-76	K∙A
ZB	SMZG3807B	GS	dz	V _Z (I _Z =6.7mA)=56B±5%; Z _{ZT} =86.00m	DO-215AA	K∙A
ZC	PDZ7.5B	PHIL	dz	V _Z =7.5B; Z _{ZT} (I _Z =5mA) = 10 Om	SOD-323, SC-76	K◆A
ZC	SMZG3808A	GS	dz	V _Z (I _Z =6.0 mA)=62 B±10%; Z _{ZT} =100.0 Om	DO-215AA	K•A
ZD	PDZ8.2B	PHIL	dz	V _Z =8.2 B; Z _{ZT} (I _Z =5 mA) = 10 Om	SOD-323, SC-76	K•A
ZD	SMZG3808B	GS	dz	V _Z (I _Z =6.0mA)=62 B±5%; Z _{ZI} =100.00m	DO-215AA	K∙A
ZE	PDZ9.1B	PHIL	dz	Vz=9.1B; ZzT (Iz=5mA)=10 Om	SOD-323, SC-76	K•A
ZE	SMZG3809A	GS	dz	V _Z (I _Z =5.5 mA) = 68 B ± 10%; Z _{ZT} = 120.0 Om	DO-215AA	K•A
ZF	PDZ10B	PHIL	dz	Vz=10B; ZzT (Iz=5 mA) = 10 Om	SOD-323, SC-76	K•A
ZF	SMZG3809B	GS	dz	V _Z (I _Z =5.5mA)=68 B±5%; Z _{ZI} =120.0 Om	DO-215AA	K∙A
ZG	PDZ11B	PHIL	dz	V _Z =11 B; Z _{ZT} (I _Z =5 mA) = 10 Om	SOD-323, SC-76	K•A
ZH	PDZ12B	PHIL	dz	V _Z =12B; Z _{ZT} (I _Z =5 mA) = 10 Om	SOD-323, SC-76	K•A
ZJ	PDZ13B	PHIL	dz	V _Z = 13 B; Z _{ZT} (I _Z = 5 mA) = 10 Om	SOD-323, SC-76	K•A
ZK	PDZ15B	PHIL	dz	V _Z =15B; Z _{ZT} (I _Z =5 мA) = 15 Oм	SOD-323, SC-76	K∙A
ZL	PDZ16B	PHIL	dz	V _Z =16B; Z _{ZT} (I _Z =5 мA) = 20 Oм	SOD-323, SC-76	K•A
ZM	PDZ18B	PHIL	dz	V _Z =18 B; Z _{ZT} (I _Z =5 мA) = 20 Oм	SOD-323, SC-76	K∙A
ZN	PDZ20B	PHIL	dz	V _Z = 20 B; Z _{ZT} (I _Z = 5 mA) = 20 Om	SOD-323, SC-76	K•A
ZP	CMDZ16L	CSI	dz	$V_Z(I_{ZT} = 0.5 \text{ mA}) = 16 \text{B}; P_0 < 250 \text{ mB} \text{T}$	SOD-323, SC-76	K•A
ZP	PDZ22B	PHIL	dz	Vz=22 B; ZzT (Iz=5 mA)=25 Om	SOD-323, SC-76	K•A
ZQ	PDZ24B	PHIL	dz	Vz=24 B; ZzT (Iz=5 mA) = 30 Om	SOD-323, SC-76	K•A
ZR	PDZ27B	PHIL	dz	V _Z =27 B; Z _{ZT} (I _Z =5 mA)=40 Om	SOD-323, SC-76	K•A
ZS	PDZ30B	PHIL	dz	V _Z =30 B; Z _{ZT} (I _Z =5 mA)=40 Cm	SOD-323, SC-76	K•A
ZT	PDZ33B	PHIL	dz	V _Z =33 B; Z _{ZT} (I _Z =5 mA)=40 Om	SOD-323, SC-76	K∙A
ZU	PDZ36B	PHIL	dz	V _z =36 B; Z _{zT} (I _z =5 mA) = 60 Om	SOD-323, SC-76	K∙A



- SOD523 SCD80 - SOD219AB SMF

SOD523/623/723, DO219, SMF

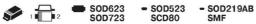
Код	Типономинал	6	Ф	Особенности	Корпус	Ц:1•2
1	BA277	PHIL	dtv	$V_R \le 35 \text{ B}; I_E \le 100 \text{ mA}; V_E (I_E = 10 \text{ mA}) \le 1.0 \text{ B}; I_R \le 0.05 \text{ mkA}; C_D \le 1.2 \text{ n}\Phi$	SOD-523, SC-79	K•A
2	BB182	PHIL	var	$V_R > 32 B$; $I_R (V_R = 30 B) < 0.01 mKA$; $C_{1B} = 5262 n\Phi$; $C_{28B} = 2.482.89 n\Phi$	SOD-523, SC-79	K•A
2	BB182	LRC	var	$V_R > 32 B$; $I_R (V_R = 30 B) < 0.01 mKA$; $C_{1B} = 5262 n\Phi$; $C_{28B} = 2.482.89 n\Phi$	SOD-523, SC-79	K•A
5	BA892	PHIL	dtv	$V_R < 35 B$; $I_F < 10 mA$; $V_F (I_F = 100 mA) < 1.0 B$; $I_R < 0.02 mkA$	SOD-523, SC-79	K∙A
7	BBY55-02V	INF	var	$V_R < 16 \text{ B}$; $I_F < 20 \text{ mA}$; $I_R < 0.003 \text{ mKA}$; $C_{1B} = 17.519.6 \text{ n}\Phi$; $C_{10B} = 5.56.5 \text{ n}\Phi$	SOD-523, SC-79	K•A
8	BB178	PHIL	var	$V_R > 32B$; $I_R (V_R = 30B) < 0.01$ mcA; $C_{1B} = 34.6542.35$ n Φ ; $C_{28B} = 2.3612.754$ n Φ	SOD-523, SC-79	K•A
8	BB178	LRC	var	$V_R > 32B$; $I_R (V_R = 30B) < 0.01$ m/kA; $C_{1B} = 34.6542.35$ m/d; $C_{28B} = 2.3612.754$ m/d	SOD-523, SC-79	K•A
8	BBY58-02V	INF	var	$V_R \le 10B$; $I_F \le 20 \text{ MA}$; $I_R \le 0.01 \text{ MKA}$; $C_{1B} = 17.519.3 \text{ m}\Phi$; $C_{4B} = 5.56.6 \text{ m}\Phi$	SOD-523, SC-79	K∙A
9	BB179	PHIL	var	$V_R > 30 B$; $I_R (V_R = 30 B) < 0.01 m/A$; $C_{1B} = 18.2221.26 n\Phi$; $C_{28B} = 1.9512.225 n\Phi$	SOD-523, SC-79	K•A
9	BB179	LRC	var	$V_R > 30 B$; $I_R (V_R = 30 B) < 0.01 mcA$; $C_{1B} = 18.2221.26 n\Phi$; $C_{28B} = 1.9512.225 n\Phi$	SOD-523, SC-79	K•A
64	BAT64-02W	INF		$V_R < 40 \text{ B}; I_E < 250 \text{ mA}; V_E (I_E = 100 \text{ mA}) < 0.75 \text{ B}; I_R < 2 \text{ mKA}; C_0 < 6 \text{ n}\Phi$	SCD-80	K•A
66	BBY56-02W	INF	var	$V_R < 10 \text{ B}; I_F < 20 \text{ mA}; I_R < 0.005 \text{ mrA}; C_{1B} = 3743 \text{ n}\Phi; C_{4B} = 12.1 \text{ n}\Phi$	SCD-80	K ∙ A
77	BBY55-02W	INF	var	$V_R < 16 \text{ B}; I_F < 20 \text{ mA}; I_R < 0.003 \text{ mrA}; C_{1B} = 17.519.6 \text{ n}\Phi; C_{10B} = 5.56.5 \text{ n}\Phi$	SCD-80	K•A
81	ZMV831BV2	ZETEX	var	$V_R < 25 \text{ B}; I_F < 200 \text{ mA}; I_R < 0.02 \text{ mrA}; C_{2B} = 14.2515.75 \text{ n}\Phi; C_{2B}/C_{20B} = 4.56.0$	SOD-523, SC-79	K∙A
82	ZMV832BV2	ZETEX	var	$V_R < 25 \text{ B}; I_E < 200 \text{ mA}; I_R < 0.02 \text{ mKA}; C_{2B} = 20.923.1 \text{ n}\Phi; C_{2B}/C_{20B} = 56.5$	SOD-523, SC-79	K∙A
88	BBY58-02W	INF	var	$V_R < 10 \text{ B}; I_F < 20 \text{ mA}; I_R < 0.01 \text{ mrA}; C_{1B} = 17.519.3 \text{ n}\Phi; C_{4B} = 5.56.6 \text{ n}\Phi$	SCD-80	K•A
91	ZV931V2	ZETEX	var	$V_R < 12 \text{ B}; I_F < 100 \text{ mA}; I_R < 0.1 \text{ mrA}; C_{2.5B} = 6.57.8 \text{ m}$	SOD-523, SC-79	K•A
92	ZV932V2	ZETEX	var	$V_R \le 12 B$; $I_F \le 100 \text{ mA}$; $I_R \le 0.1 \text{ mrA}$; $C_{2.5B} = 8.510.5 \text{ n}$	SOD-523, SC-79	K∙A
93	ZV933V2	ZETEX	var	$V_R \le 12 \text{ B}; I_F \le 100 \text{ mA}; I_R \le 0.1 \text{ mrA}; C_{2.58} = 1827 \text{ n}\Phi$	SOD-523, SC-79	K∙A
0	BZX584C5V6-02V	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA})=5.26 \text{ B}; Z_{ZT}<40 \text{ Om}$	SOD-523, SC-79	K•A
0	JDS2S03S	TOSH	di	$V_R < 30 \text{ B; } I_F < 100 \text{ mA; } V_F (I_F = 2 \text{ mA}) < 0.85 \text{ B; } I_R < 0.1 \text{ m/sA; } C_D < 1.2 \text{ n}\Phi$	SOD-623	K•A
1	BZX584C16-02V	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 15.317.1 \text{ B}; Z_{ZT} < 40 \text{ Om}$	SOD-523, SC-79	K•A
1	BZX584C22-02V	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 21.622.4 \text{ B}; Z_{ZT} < 55 \text{ Om}$	SOD-523, SC-79	K•A
1	BZX584C5V1-02V	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 4.85.4 \text{ B}; Z_{ZT} < 60 \text{ Om}$	SOD-523, SC-79	K∙A
1	BZX584C6V2-02V	VISH	dz	$V_Z(I_{ZT}=5\text{ mA})=5.86.6\text{ B}; Z_{ZT}<10\text{ Om}$	SOD-523, SC-79	K∙A
2	BZX584C18-02V	VISH	dz	$V_z(I_{zt} = 5 \text{ mA}) = 16.819.1 \text{ B; } Z_{zt} < 45 \text{ Om}$	SOD-523, SC-79	K•A
2	BZX584C2V4-02V	VISH	dz	$V_z(I_{zT}=5\text{ mA})=2.22.6\text{ B}; Z_{zT}<100\text{ Om}$	SOD-523, SC-79	K•A
2	BZX584C6V8-02V	VISH	dz	$V_Z(I_{ZT}=5\text{ mA})=6.47.2\text{ B; }Z_{ZT}<15\text{ Om}$	SOD-523, SC-79	K•A
3	BZX584C2V7-02V	VISH	dz	$V_Z(I_{ZT}=5\text{ mA})=2.52.9\text{ B; } Z_{ZT}<100\text{ Om}$	SOD-523, SC-79	K•A
3	BZX584C7V5-02V	VISH	dz	$V_z(I_{ZT}=5\text{mA})=77.9\text{ B}; Z_{ZT}<15\text{ Om}$	SOD-523, SC-79	K•A
4	BB664-02V	INF	var	$V_R < 30 \text{ B}; I_F < 20 \text{ mA}; I_R < 0.01 \text{ mrA}; C_{1B} = 3944.5 \text{ n}\Phi; C_{28B} = 2.42.75$	SOD-523, SC-79	K•A
4	BZX584C15-02V	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 13.815.6 \text{ B}; Z_{ZT} < 30 \text{ Om}$	SOD-523, SC-79	K•A
4	BZX584C20-02V	VISH	dz	$V_z(I_{zT}=5 \text{ mA})=18.821.2 \text{ B}; Z_{zT}<55 \text{ Om}$	SOD-523, SC-79	K•A
4	BZX584C3V0-02V	VISH	dz	$V_z(I_{zT}=5\text{ mA})=2.83.2\text{ B; } Z_{zT}<95\text{ Om}$	SOD-523, SC-79	K•A
44	BB664	INF	var	$V_R < 30 \text{ B}; I_F < 20 \text{ mA}; I_R < 0.01 \text{ mrA}; C_{1B} = 3944.5 \text{ n}\Phi; C_{28B} = 2.42.75$	SCD-80	K•A
5	BBY57-02V	INF	var	$V_R < 10 \text{ B}; I_F < 20 \text{ mA}; I_R < 0.01 \text{ mrA}; C_{1B} = 16.518.6 \text{ n}\Phi; C_{4B} = 3.55.5 \text{ n}\Phi$	SOD-523, SC-79	K•A
5	BZX584C13-02V	VISH	dz	$V_Z(I_{ZT}=5\text{ mA})=12.414.1\text{ B}; Z_{ZT}<30\text{ Om}$	SOD-523, SC-79	K∙A
5	BZX584C24-02V	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 22.823.3 \text{ B}; Z_{ZT} < 70 \text{ Om}$	SOD-523, SC-79	K∙A
5	BZX584C3V3-02V	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 3.13.5 \text{ B}; Z_{ZT} < 95 \text{ Om}$	SOD-523, SC-79	K•A
55	BBY57-02W	INF	var	$V_R < 10 \text{ B}; I_F < 20 \text{ mA}; I_R < 0.01 \text{ mrA}; C_{1B} = 16.518.6 \text{ n}\Phi; C_{4B} = 3.55.5 \text{ n}\Phi$	SCD-80	K•A
6	BAS16-02V	INF	di	$V_R < 80 \text{ B}; I_F < 200 \text{ mA}; V_F (I_F = 150 \text{ mA}) < 1.25 \text{ B}; I_R < 50 \text{ mKA}$	SOD-523, SC-79	K∙A
6	BZX584C3V6-02V	VISH	dz	V _Z (I _{ZT} =5mA)=3.43.8 B; Z _{ZT} <90 Om	SOD-523, SC-79	K∙A
62	BAT62-02W	INF	shd	$V_R < 40 \text{ B}; I_F < 20 \text{ mA}; V_F (I_F = 2 \text{ mA}) < 1 \text{ B}; I_R < 10 \text{ mrA}; C_D < 0.6 \text{ n}\Phi$	SCD-80	K•A
7	BZX584C12-02V	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 11.412.7 \text{ B}; Z_{ZT} < 25 \text{ Om}$	SOD-523, SC-79	K•A
7	BZX584C27-02V	VISH	dz	$V_Z(I_{ZT}=2mA)=25.128.9B; Z_{ZT}<800m$	SOD-523, SC-79	K•A
7	BZX584C3V9-02V	VISH	dz	$V_Z(I_{ZT}=5\text{ mA})=3.74.1 \text{ B; } Z_{ZT}<90 \text{ Om}$	SOD-523, SC-79	K•A
73	BAS70-02W	INF	shd	$V_R < 70 \text{ B}; I_F < 70 \text{ mA}; V_F (I_F = 15 \text{ mA}) < 1.0 \text{ B}; I_R < 0.1 \text{ m/A}; C_D < 2.0 \text{ n}\Phi$	SCD-80	K•A
8	BZX584C4V3-02V	VISH	dz	$V_2(I_{2T} = 5 \text{ mA}) = 4.04.6 \text{ B}; Z_{2T} < 90 \text{ Om}$	SOD-523, SC-79	K•A

- SOD623 SOD723





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A 188400 ROHM di V _R <808 B, W ₁ <225MA, V _F (W ₁ =100MA)<1.2 B, I _R <0.1 kmA, I _{RR} <4 Hc SOD-A B8992-02L NF di V _R <538 B, K 10 MA, V _F (W ₁ =100 MA)<1.0 B, I _R <0.0 2 kmA SOD-A SOD-A JOVS06S TOSH var V _R <10 B, I _R <10 MA, V _F (W ₁ =100 MA)<1.0 B, I _R <0.0 2 kmA SOD-A JOVS06S TOSH var V _R <10 B, I _R <10 MA, V _F (W ₁ =10 MA)<1.1 E, I _R <0.1 kmA, I _{RR} <4 Hc SOD-A JOVS06S TOSH var V _R <10 B, I _R <10 MA, V _F (W ₁ =10 MA)<1.1 E, I _R <0.1 kmA, I _{RR} <4 Hc SOD-A JOVS06S TOSH var V _R <10 B, I _R <10 MA, V _F (W ₁ =10 B, I _R <0.0 MA, V _F (W ₁ =10 B, I _R <0.0 MA, I _R <0.0 E, I _R <0.0 E, I _R <0.0 MA, I _R <0.0 E, I _R <0.0 MA, I _R <0.0 E, I _R <0.0 E, I _R <0.0 MA, I _R <0.0 E, I _R <0.0 E, I _R <0.0 MA, I _R <0.0 E,	523, SC-79 523, SC-79 623 523, SC-79 523, SC-79 523, SC-79 80 80 80 623 523, SC-79 523, SC-79 623 523, SC-79 523, SC-79 523, SC-79 623	K•A
A BA892-02L INF div V _R <358 _E <10mA V _F (I _E =100mA)<1.08 _R <0.02mA SOD-MA SOD-MA INFO _R <10 _R <10.08 _R <0.02mA SOD-MA _R <10 _R <10.08 _R <0.00 _R <10 _R <10.08 _R <10.00 _R <10	523, SC-79 623 523, SC-79 523, SC-79 523, SC-79 80 80 80 623 523, SC-79 523, SC-79 623 523, SC-79 623 523, SC-79 623	K•A K•A K•A K•A K•A K•A K•A K•A K•A
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	623 523, SC-79 523, SC-79 80 80 80 623 523, SC-79 523, SC-79 623 523, SC-79 623 523, SC-79	K•A K•A K•A K•A K•A K•A K•A K•A
A,4 ISS400 WEIT di V _N < 80.8 L _N < 100.MA, V _F (I _F = 100.MA) < 1.2 B. I _N < 0.1 MMA. I _{TRR} < 4 Hz	523, SC-79 523, SC-79 80 80 80 623 523, SC-79	K•A K•A K•A K•A K•A K•A K•A K•A
Al B8208-02 PHIL var V _R >10B V _R V	523, SC-79 523, SC-79 80 80 623 523, SC-79 523, SC-79 523, SC-79 623 523, SC-79 523, SC-79 523, SC-79	K•A K•A K•A K•A K•A K•A K•A
A2 BB184 PHIL var V ₈ >138, k ₁ k ₁ k ₃ =10B\cdot 0.01 kmA, C ₁₈ =127153 rdp, C ₁₈₈ =1.872.13 rdp SOD- A6 BA516-02W INF ci V ₈ <808 k ₁ k ₂ <20 kmA, V ₁ k ₁ =150 kmA \cdot 1.25 k k ₁ k ₂ <50 kmA SOD- AA BA992 INF cir V ₈ <308 k ₁ k ₂ <20 kmA, V ₁ k ₁ =150 kmA \cdot 1.25 k k ₁ k ₂ <50 kmA SOD- AA BA992 INF cir V ₈ <308 k ₁ k ₂ 0.004 k ₁ k ₁ <0.01 kmA, C ₁₈ =17.520 rdp, C ₁₈ C ₂₈₈ =8.29.8 SOD- B BB555 SOD INF cir V ₈ <308 k ₁ k ₂ 0.003 kmA, C ₁₈ =9711 rdp, C ₁₈ =4.455.45 SOD- BB BB555-02V INF cir V ₈ <308 k ₁ k ₂ 0.003 kmA, C ₁₈ =9711 rdp, C ₁₈ =4.455.45 SOD- C BB198 PHIL v ₁ k ₁ v ₁ k ₂ >328 k ₁ k ₁ 0.01 kmA, C ₁₈ =11250 rdp, C ₁₈ C ₂₈₈ =8.29.8 SOD- C BD7856 SOV INF cir V ₈ <308 k ₁ k ₂ 0 kMA, k ₁ C ₁₈ 1 rdp, C ₁₈	523, SC-79 80 80 80 623 523, SC-79 523, SC-79 623 523, SC-79 523, SC-79 523, SC-79	K•A K•A K•A K•A K•A K•A
A6 BAS16-02W INF di V _R <808, IK-200MA, V _F (I _F =150MA)<1.25 B, I _R <50MAA SCD- A8 BAS92 INF di V _F <35 B, I _K <10MA, V _F (I _F =150MA)<1.25 B, I _R <50 MAA SCD- B8 BS555 INF dar V _R <308, I _K <200MA, I _R <0.01 ImrA, C ₁₈ =17520 m ² C, C ₁₈ C ₀₈₈ =8.29.8 SCD- B8 BS555-02V INF dar V _R <308, I _K <200MA, I _R <0.01 ImrA, C ₁₈ =17520 m ² C, C ₁₈ C ₀₈₈ =8.29.8 SCD- B8 BS55-02V INF dar V _R <308, I _K <200MA, I _R <0.01 ImrA, C ₁₈ =17520 m ² C, C ₁₈ C ₀₈₈ =8.29.8 SCD- C6 BS179B PHIL dar V _R <328, I _K V _R =308, I _K <0.001 ImrA, C ₁₈ =18.2220 m ² C, C ₁₈ C ₂₈₈ =911 SCD- C7 JOV2806S TOSH dar V _R <308, I _K <200MA, I _R <0.01 ImrA, C ₁₈ =18521.5 m ² C, C ₁₈ C ₂₈₈ =911 SCD- C8 JOV2806S TOSH dar V _R <308, I _K <200MA, I _R <0.01 ImrA, C ₁₈ =18521.5 m ² C, C ₁₈ C ₂₈₈ =911 SCD- C9 JOV2806S TOSH dar V _R <308, I _K <200MA, I _R <0.01 ImrA, C ₁₈ =18521.5 m ² C, C ₁₈ C ₂₈₈ =911 SCD- C0 JOV2806S PSV6 PHIL dz V _X (I _{X1} =5 MA)=2.5 A, 5.7 IB. Z ₁₇ <40 CM SCD- C1 ISX585-BSV6 PHIL dz V _X (I _{X1} =5 MA)=2.5 A, 5.7 IB. Z ₁₇ <40 CM SCD- C2 BZX686-BSV7 PHIL dz V _X (I _{X1} =5 MA)=2.8 S, 2.7 S, B. Z ₁₇ <50 CM SCD- C3 BZX585-BSV8 PHIL dz V _X (I _{X1} =5 MA)=3.33 S, 7B. Z ₁₇ <50 CM SCD- C5 BZX685-BSV9 PHIL dz V _X (I _{X1} =5 MA)=3.33 S, 7B. Z ₁₇ <50 CM SCD- C6 BZX685-BSV9 PHIL dz V _X (I _{X1} =5 MA)=3.33 G, B. Z ₁₇ <50 CM SCD- C7 BZX585-BSV9 PHIL dz V _X (I _{X1} =5 MA)=3.33 G, B. Z ₁₇ <50 CM SCD- C8 BZX685-BSV9 PHIL dz V _X (I _{X1} =5 MA)=3.33 G, B. Z ₁₇ <59 CM SCD- C7 BZX585-BSV9 PHIL dz V _X (I _{X1} =5 MA)=3.23 BB. Z ₁₇ <59 CM SCD- C8 BZX685-BSV9 PHIL dz V _X (I _{X1} =5 MA)=3.23 BB. Z ₁₇ <59 CM SCD- C9 BZX685-BSV9 PHIL dz V _X (I _{X1} =5 MA)=3.23 BB. Z ₁₇ <59 CM SCD- C9 BZX685-BSV9 PHIL dz V _X (I _{X1} =5 MA)=3.23 BB. Z ₁₇ <59 CM SCD- C9 BZX685-BSV9 PHIL dz V _X (I _{X1} =5 MA)=3.23 BB. Z ₁₇ <59 CM SCD- C9 BZX685-BSV9 PHIL dz V _X (I _{X1} =5 MA)=3.23 BB. Z ₁₇ <59 CM SCD- C9 BZX685-BSV9 PHIL dz V _X (I _{X1} =5 MA)=3.23 BB. Z ₁₇ <59 CM SCD- C9 BZX685-BSV9 PHIL dz V _X (I _{X1} =5 MA)=3.23 BB. Z ₁₇ <59 CM SCD- C9 BZX6	80 80 623 523, SC-79 523, SC-79 523, SC-79 623 523, SC-79 523, SC-79	K•A K•A K•A K•A K•A K•A
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	80 80 623 523, SC-79 523, SC-79 523, SC-79 623 523, SC-79 523, SC-79	K•A K•A K•A K•A K•A
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	80 623 523, SC-79 523, SC-79 523, SC-79 623 523, SC-79 523, SC-79	K•A K•A K•A K•A
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	623 523, SC-79 523, SC-79 523, SC-79 623 523, SC-79 523, SC-79	K•A K•A K•A
BB B8555-02V NF var V _R < 308 x < 20 MA, I ₈ < 0.0 1 marA, C ₁₈ = 17.5 20 rd, C ₁₈ C ₂₈₈ = 8 2 9.8 SOD-	523, SC-79 523, SC-79 523, SC-79 623 523, SC-79 523, SC-79	K•A K•A K•A
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	523, SC-79 523, SC-79 623 523, SC-79 523, SC-79	K•A K•A
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$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	523, SC-79	K•A
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	523, SC-79	
D JDV2S07S TOSH var $V_R < 10 B$; $I_R < 0.003 \text{ km/A}$; $C_{1B} = 4.04.9 \text{ n}\Phi$; $C_{4B} = 1.852.35$ SOD-	80	K•A
		K•A
D0 BZD27C3V6P VISH dz $V_y(I_{2T} = 100 \text{ mA}) = 3.43.8 \text{ B}; Z_{yy} < 80 \text{ m}$ D0-2	19AB, SMF	K•A
	19AB, SMF	K•A
	19AB, SMF	K•A
The Control of the Co	19AB, SMF	
	19AB, SMF	
	19AB, SMF	K•A
	19AB SMF	K•A
D7 BZD27C6V8P VISH dz $V_z(I_{zz}=100 \text{ mA})=6.47.2 \text{ B; } Z_{zz}<3 \text{ Cm}$ DO-2	19AB, SMF	K•A
D8 BZD27C7V5P VISH dz $V_z(I_{zT}=100 \text{ mA})=77.9B; Z_{zT}<2 \text{ Cm}$ DO-2	19AB, SMF	K•A
	19AB, SMF	K•A
DE BB659 INF var V _R <30 B; I _r <20 mA; I _R <0.01 mrA; C _{1 B} =3640 nФ; C _{1 B} /C _{28 B} =14.7 SCD-	80	K•A
	523, SC-79	K•A
E JDV2S13S TOSH var $V_B < 10 B$; $I_B < 0.003 \text{ mrA}$; $C_{1B} = 5.76.7 \text{ n}\Phi$; $C_{4B} = 1.852.45$ SOD-	623	K•A
	19AB, SMF	K•A
	523, SC-79	K•A
	19AB, SMF	K•A
E1 BZX585-B6V2 PHIL dz Vz (Izt=5 mA) = 6.086.32 B; Zzt < 10 Om SOD-	523, SC-79	K•A
	19AB, SMF	K•A
		-
TOTAL DESCRIPTION OF THE PROPERTY OF THE PROPE	19AB, SMF	V - A
	19AB, SMF 523, SC-79	N-A
E4 BZX585-B8V2 PHIL dz Vz(Izr=5 mA)=8.048.36 B; Zzr<10 0m SOD-	19AB, SMF 523, SC-79 19AB, SMF	



Б Ф Особенности	Корпус	Ц:1•
VISH dz V _Z (I _{ZT} =50mA)=13.815.6 B; Z _{ZT} <10 0m	DO-219AB, SMF	K • A
PHIL dz V _Z (I _{ZT} =5mA)=8.929.28 B; Z _{ZT} <10 Om	SOD-523, SC-79	K • A
VISH dz $V_Z(I_{ZT} = 25 \text{ mA}) = 15.317.1 \text{ B}; Z_{ZT} \le 15 \text{ Om}$	DO-219AB, SMF	K • A
PHIL dz $V_z(I_{ZT}=5\text{mA})=9.810.2\text{ B}; Z_{ZT}<10\text{ Om}$	SOD-523, SC-79	K•A
VISH dz V _Z (I _{ZT} =25mA)=16.819.1B; Z _{ZT} <15.0m	DO-219AB, SMF	K • A
PHIL dz $V_z(I_{ZT}=5\text{ mA})=10.811.2\text{ B}; Z_{ZT}<10\text{ Om}$	SOD-523, SC-79	K•A
VISH dz $V_2(I_{2T} = 25 \text{ mA}) = 18.821.2 \text{ B}; Z_{2T} < 15 \text{ Om}$	DO-219AB, SMF	K • A
PHIL dz $V_z(I_{zz}=5\text{ mA})=11.812.2\text{ B}; Z_{zz}<10\text{ Om}$	SOD-523, SC-79	K•A
VISH dz $V_z(I_{zz} = 25 \text{ mA}) = 20.823.3 \text{ B; } Z_{zz} \le 15 \text{ Om}$	DO-219AB, SMF	K • A
PHIL dz V _z (I _{zz} =5mA)=12.713.3B;Z _{zz} <10.0m	SOD-523, SC-79	K.
INF var V _B <30 B; I _F <20 mA; I _B <0.01 mkA; C _{1B} =5161.5nΦ; C _{28B} =2.5		K • A
SIEM di $V_R < 150B$; $I_E < 200 \text{ mA}$; $V_E (I_E = 100 \text{ mA}) < 1.0 B$; $I_R < 0.1 \text{ m/sA}$; $C_D < 5$		K • A
INF var V _B <15 B, I _F <50 mA; I _B <0.01 mκA; C _{1 B} =20.25 πΦ; C4.7V=2.62		
TOSH var V _R <10 B; I _R <0.003 мкA; C _{0.5B} =7.38.4 μΦ; C _{2.5B} =2.753.4	SOD-623	K • A
VISH dz V _Z (I _{ZT} =25MA)=22.825.6 B; Z _{ZT} <15.0M	DO-219AB. SMF	
PHIL dz V _Z (I _{ZT} =5mA)=5.325.88 B; Z _{ZT} <40 Om	SOD-523, SC-79	11000
CSI dz V ₂ =5.6B(5%); P ₀ <350 мBт	SOD-523, SC-79	
VISH dz V ₂ (I ₂₇ = 25 MA) = 25.128.9 B; Z ₂₇ < 15 OM	DO-219AB, SMF	
	SOD-523, SC-79	
PHIL dz V _Z (I _{ZT} =5mA) = 2.282.52 B; Z _{ZT} < 100 Om		
CSI dz V _Z =2.4B(5%); P _D <350 MBT	SOD-523, SC-79	
CSI dz V _Z =2.6B(5%); P _D <350 MB _T	SOD-523, SC-79	
VISH dz V _Z (I _{ZT} = 25 mA) = 2832 B; Z _{ZT} < 15 Om	DO-219AB, SMF	_
PHIL dz V _Z (I _{ZT} =5mA)=2.572.84 B; Z _{ZT} <100 Om	SOD-523, SC-79	
CSI dz V _Z =2.7B(5%); P _D <350 mBT	SOD-523, SC-79	
VISH dz V _Z (I _{ZT} = 25 mA) = 3135 B; Z _{ZT} < 15 Om	DO-219AB, SMF	
PHIL dz $V_z(I_{ZT}=5 \text{ mA})=2.853.15 \text{ B}; Z_{ZT} \le 95 \text{ Om}$	SOD-523, SC-79	
CSI dz V _Z =3.0 B(5%); P _D <350 mB _T	SOD-523, SC-79	K•A
VISH dz V _Z (I _{ZT} = 10 mA) = 3438 B; Z _{ZT} < 40 Om	DO-219AB, SMF	K • A
PHIL dz V _Z (I _{ZT} =5mA)=3.143.47 B; Z _{ZT} <95 Om	SOD-523, SC-79	K•A
CSI dz V _Z =3.3 B(5%); P _D <350 mB _T	SOD-523, SC-79	K•A
VISH dz V _Z (I _{ZT} =10mA)=3741 B; Z _{ZT} <40 Om	DO-219AB, SMF	K • A
PHIL dz $V_2(I_{2T}=5\text{ mA})=3.423.78 \text{ B}; Z_{2T}<90 \text{ Om}$	SOD-523, SC-79	K•A
CSI dz V _z =3.6 B (5%); P _D < 350 mBT	SOD-523, SC-79	K•A
VISH dz V _Z (I _{ZT} = 10 mA) = 4046 B; Z _{ZT} < 45 Om	DO-219AB, SMF	K • A
PHIL dz V ₂ (I ₂₇ = 5 mA) = 3.714.10 B; Z ₂₇ < 90 Om	SOD-523, SC-79	K•A
CSI dz V _z =3.9B(5%); P _D <350 MBT	SOD-523, SC-79	K•A
VISH dz $V_z(I_{zx} = 10 \text{ mA}) = 4450 \text{ B}; Z_{zx} < 45 \text{ Om}$	DO-219AB, SMF	
PHIL dz $V_z(I_{zz} = 5 \text{ mA}) = 4.094.52 \text{ B}; Z_{zz} \le 90 \text{ Om}$	SOD-523, SC-79	
CSI dz V _z = 4.3 B (5%); P _D < 350 mB _T	SOD-523, SC-79	
VISH dz V _z (I _{zz} = 10 mA) = 4854 B; Z _{zz} < 60 Om	DO-219AB, SMF	
PHIL dz V ₇ (I ₇₇ =5mA)=4.474.94 B; Z ₇₇ <80 Om	SOD-523, SC-79	_
CSI dz V ₇ =4.7B(5%); P _D < 350 mBT	SOD-523, SC-79	
VISH dz $V_2(I_{2T} = 10 \text{ MA}) = 5260 \text{ B; } Z_{2T} < 60 \text{ Om}$	DO-219AB, SMF	
PHIL dz V ₂ (I _{2T} =5mA)=4.855.36 B; Z _{2T} <60 Om	SOD-523, SC-79	00/2012/
CSI dz V ₂ (1 ₂ T = 5MA) = 4.655.36 B, Z ₂ T < 60 GM	SOD-523, SC-79	
2 1 11 0		
1 10	SOD-523, SC-79	
1.0	SOD-523, SC-79	
TOSH var V _B <10 B; I _B <0.003 mkA; C _{1B} =3.854.55 nФ; C _{4B} =1.942.48	SOD-523, SC-79	
TOSH var V _R <10 B; I _R <0.003 мкA; C _{1 B} =4449.5 πΦ; C _{4 B} =9.212	SOD-523, SC-79	
INF pin $V_R < 50 \text{ B}; I_F < 100 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 1.2 \text{ B}; I_R < 0.01 \text{ mKA}$	SOD-523, SC-79	
TOSH var $V_R < 10 B$; $I_R < 0.003 \text{ mrA}$; $C_{1B} = 2.853.45 \text{ n}\Phi$; $C_{4B} = 1.351.81$	SOD-623	K•≠
VISH dz V _Z (I _{ZT} = 10 mA) = 5866 B; Z _{ZT} < 80 Om	DO-219AB, SMF	

- SOD623 SOD723

■ SOD523 ■ SOD219AB SMF





Код	Типономинал	Б	Φ	Особенности	Корпус	Ц:1•2
G1	BZD27C68P	VISH	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 6472 \text{ B}; Z_{ZT} < 80 \text{ Om}$	DO-219AB, SMF	K∙A
G2	BZD27C75P	VISH	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 7079 \text{ B}; Z_{ZT} < 100 \text{ Om}$	DO-219AB, SMF	K•A
G3	BZD27C82P	VISH	dz	$V_Z(I_{ZT} = 10 \text{ mA}) = 7787 \text{ B}; Z_{ZT} < 100 \text{ Om}$	DO-219AB, SMF	K•A
G4	BZD27C91P	VISH	dz	V _Z (I _{ZT} =5 mA)=8596 B; Z _{ZT} <200 Om	DO-219AB, SMF	K•A
G5	BZD27C100P	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA})=94106 \text{ B}; Z_{ZT}<200 \text{ Om}$	DO-219AB, SMF	K•A
G6	BZD27C110P	VISH	dz	$V_z(I_{zT}=5 \text{ mA})=104116 \text{ B}; Z_{zT}<250 \text{ Om}$	DO-219AB, SMF	K•A
G7	BZD27C120P	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 114127 \text{ B}; Z_{ZT} < 250 \text{ Om}$	DO-219AB, SMF	K•A
G8	BZD27C130P	VISH	dz	$V_{z}(I_{zz}=5 \text{ mA})=124141 \text{ B; } Z_{zz}<300 \text{ Om}$	DO-219AB, SMF	K•A
G9	BZD27C150P	VISH	dz	V _z (I _{zz} =5 mA) = 138156 B; Z _{zz} < 300 Om	DO-219AB, SMF	K∙A
GG	BAR63-02W	INF	pin	$V_B \le 50 \text{ B; } I_E \le 100 \text{ mA; } V_E (I_E = 100 \text{ mA}) \le 1.2 \text{ B; } I_B \le 0.01 \text{ mKA}$	SCD-80	K•A
Н	BB141	PHIL	var	$V_B > 6 B; I_B (V_B = 6 B) < 0.01 \text{ m/KA}; C_{1B} = 3.94.5 \text{ n/D}; C_{4B} = 2.222.55 \text{ n/D}$	SOD-523, SC-79	K•A
Н	BB141	LRC	var	$V_B > 6 B; I_B (V_B = 6 B) < 0.01 \text{ m/KA}; C_{1B} = 3.94.5 \text{ n/D}; C_{4B} = 2.222.55 \text{ n/D}$	SOD-523, SC-79	K•A
Н	BB659C-02V	INF		$V_B < 30 \text{ B}; I_E < 20 \text{ mA}; I_B < 0.01 \text{ m/sA}; C_{1B} = 36.542 \text{ n}\Phi; C_{1B}/C_{28B} = 15.3$	SOD-523, SC-79	K•A
Н	JDV2S02S	TOSH		$V_B < 10 \text{ B}; I_B < 0.003 \text{ mKA}; C_{1B} = 1.82.3 \text{ n}\Phi; C_{4B} = 0.831.23$	SOD-623	K•A
HO	BZD27C160P	VISH		V _Z (I _{ZT} = 5 mA) = 153171 B; Z _{ZT} < 350 Om	DO-219AB, SMF	K•A
	BZX585-C15	PHIL		V _Z (I _{ZT} = 5 mA) = 14.2515.75 B; Z _{ZT} < 15 Om	SOD-523, SC-79	
-	CMOZ15V	CSI		Vz=15 B (5%); P _D <350 mBr	SOD-523, SC-79	-
	BZD27C180P	VISH		V _Z (I _{ZT} =5 MA) = 168191 B; Z _{ZT} < 400 OM	DO-219AB, SMF	
_	BZX585-C6V2	PHIL	dz	V _Z (I _{ZT} =5MA)=5.896.51 B; Z _{ZT} <10 OM	SOD-523, SC-79	
103	CMOZ6V2	CSI		V _z =6.2B(5%); P _D <350mBt	SOD-523, SC-79	
(5.55	BZD27C200P	VISH	dz	$V_Z(I_{ZT}=5 \text{ MA})=188212 \text{ B; } Z_{ZT}<500 \text{ Om}$	DO-219AB, SMF	
	BZX585-C6V8	PHIL	dz	V _Z (I _{ZT} =5 MA)=6.46Z.14 B; Z _{ZT} <10 OM	SOD-523, SC-79	
	CMOZ6V8	CSI	dz	V _Z =6.8 B(5%); P _D <350 MBT	SOD-523, SC-79	_
	BZX585-C7V5	PHIL	dz	V _Z (I _{ZT} =5 MA) = 7.137.88 B; Z _{ZT} < 10 OM	SOD-523, SC-79	_
	CMOZ7V5	CSI		V _z =7.5B(5%), P _p <350MBT	SOD-523, SC-79	
	BZX585-C8V2	PHIL	dz	V _Z (I _{ZT} =5 MA)=7.798.61 B; Z _{ZT} <10 OM	SOD-523, SC-79	
	CMOZ8V2	CSI	1000	V _Z =8.2 B(5%), P _D <350 MBT	SOD-523, SC-79	
	BZX585-C9V1	PHIL	1000	V _Z (I _{ZT} =5 MA)=8.659.56 B; Z _{ZT} <10 OM	SOD-523, SC-79	
	CMOZ9V1	CSI		V _Z ((ZT = 5 MA) = 8.659.56 B, ZZT < 10 OM V _Z = 9.1 B (5%), P _D < 350 MBT	SOD-523, SC-79	
_	BZX585-C10	PHIL			SOD-523, SC-79	_
27.77	0.000	1127779555		V _Z (I _{ZT} =5 MA)=9.510.5B; Z _{ZT} <10 Om		
	CMOZ10V	CSI	_	V _Z = 10 B (5%); P _D < 350 mBT	SOD-523, SC-79	
	BZX585-C11	PHIL	dz	V _Z (I _{ZT} =5 MA) = 10.4511.55 B; Z _{ZT} < 10 OM	SOD-523, SC-79	
	CMOZ11V	CSI	-	V _Z =11B(5%); P _D <350 mBT	SOD-523, SC-79	_
-	BZX585-C12	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 11.412.6 B; Z _{ZT} < 10 Om	SOD-523, SC-79	
	CMOZ12V	CSI		V _Z =12B(5%), P _D <350 mBr	SOD-523, SC-79	
	BZX585-C13	PHIL	-	$V_Z(I_{ZT}=5 \text{ mA}) = 12.3513.65 \text{ B}; Z_{ZT} < 10 \text{ Om}$	SOD-523, SC-79	
	CMOZ13V	CSI	dz	$V_Z = 13 B(5\%); P_D < 350 MBT$	SOD-523, SC-79	1200
	BB659C	INF		$V_R < 30 \text{ B}; I_F < 20 \text{ mA}; I_R < 0.01 \text{ mrA}; C_{1B} = 36.542 \text{ n}\Phi; C_{1B}/C_{28B} = 15.3$	SCD-80	K•A
	BBY51-02W	INF	-	$V_R < 7B$; $I_F < 20$ mA; $I_R < 0.01$ mKA; $C_{1B} = 5.055.75$ n Φ ; $C4V = 2.53.7$ n Φ	SCD-80	K•A
	CMOZ39V	CSI	dz	V _Z =39 B (5%); P _D <350 mB _T	SOD-523, SC-79	
	CMOZ16V	CSI	dz	V _Z = 16 B (5%); P _D < 350 mBr	SOD-523, SC-79	
J2	CMOZ18V	CSI	dz	$V_Z = 18 B(5\%); P_D < 350 MBT$	SOD-523, SC-79	
1000	CMOZ20V	CSI		V _Z = 20 B (5%); P _D < 350 мВт	SOD-523, SC-79	
3.5	CMOZ22V	CSI	dz	$V_Z = 22 B (5\%); P_0 < 350 mBT$	SOD-523, SC-79	
_	CMOZ24V	CSI	dz	V _Z = 24 B (5%); P _D < 350 мВт	SOD-523, SC-79	_
	CMOZ27V	CSI	dz	V _Z =27B(5%); P _D <350 mBT	SOD-523, SC-79	
J7	CMOZ30V	CSI	dz	V _Z =30 B (5%); P _D <350 мВт	SOD-523, SC-79	
0.00	CMOZ33V	CSI	dz	V _Z = 33 B (5%); P _D < 350 мВт	SOD-523, SC-79	
J9	CMOZ36V	CSI	dz	V _Z = 36 B (5%); P _D < 350 мВт	SOD-523, SC-79	K•A
K	BB142	PHIL	var	$V_R > 6 B$, $I_R (V_R = 6 B) < 0.01 \text{ m/A}$; $C_{1B} = 44.9 \text{ n}\Phi$; $C_{4B} = 1.852.35 \text{ n}\Phi$	SOD-523, SC-79	K•A
K	BB142	LRC	var	$V_B > 6 B$; $I_B (V_B = 6 B) < 0.01 mKA$; $C_{1B} = 44.9 n\Phi$; $C_{4B} = 1.852.35 n\Phi$	SOD-523, SC-79	K•A
K	BB679-02V	INF	var	$V_B < 30 \text{ B}; I_F < 20 \text{ mA}; I_B < 0.01 \text{ mrA}; C_{1B} = 43.551.5 \text{ n}\Phi; C_{2BB} = 2.42.8$	SOD-523, SC-79	K•A



SOD623 - SOD523 - SOD219AB SOD723 - SOD523 - SOD523 SCD80 - SMF

Код	Типономинал	6	Φ	Особенности	Корпус	Ц:1•
K	BZX584C30-02V	VISH	dz	$V_z(I_{zT} = 2 \text{ mA}) = 2832 \text{ B; } Z_{zT} < 80 \text{ Om}$	SOD-523, SC-79	K•A
K	JDV2S05S	TOSH	var	V _B < 10 B; I _B < 0.003 мкА; С _{1 B} = 3.854.55 пФ; С _{4 B} = 1.942.48	SOD-623	K•A
K 1	CMOZ43V	CSI	dz	Vz = 43 B (5%); Po < 350 mBT	SOD-523, SC-79	K•A
K3	BB145C	PHIL	var	V _B > 10 B; I _B (V _B = 15 B)< 0.003 mrA; C _{1 B} = 6.47.2nΦ; C _{4 B} = 2.552.85 nΦ	SOD-523, SC-79	K•/
KK	BBY52-02W	INF	var	$V_B < 7B$; $I_E < 20$ mA; $I_B < 0.01$ mkA; $C_{1B} = 1.42.2$ n Φ ; $C_{4B} = 0.851.45$ n Φ	SCD-80	K•/
L	BB143	PHIL	var	$V_B > 6B$; $I_B(V_B = 6B) < 0.01$ mrA; $C_{1B} = 4.755.75$ n Φ ; $C_{4B} = 2.052.55$ n Φ	SOD-523, SC-79	K•
L	BB143	LRC	var	$V_B > 6 B$; $I_B (V_B = 6 B) < 0.01 mkA$; $C_{1B} = 4.755.75 n\Phi$; $C_{4B} = 2.052.55 n\Phi$	SOD-523, SC-79	K•/
L	BBY53-02V	INF	var	V _B < 6 B; I _E < 20 мА; I _B < 0.01 мкА; С _{1 B} = 4.85.8 пФ; С _{3 B} = 1.853.1 пФ	SOD-523, SC-79	
L	BZX584C47-02V	VISH	dz	$V_z(I_{zz} = 2 \text{ mA}) = 4450 \text{ B}; Z_{zz} < 170 \text{ Om}$	SOD-523, SC-79	
L2	BB202	PHIL		V _B >6B; I _B (V _B =6B)<0.01мкА; C0.2V=28.233.5 пФ; C2.3V=7.211.2 пФ	SOD-523, SC-79	
ш	BBY53-02W	INF		$V_R < 6B$; $I_F < 20$ mA; $I_R < 0.01$ mKA; $C_{1B} = 4.85.8$ n Φ ; $C_{3B} = 1.853.1$ n Φ	SCD-80	K•/
M	BAR64-02W	SIEM		$V_B < 200B$; $I_F < 100$ MA; $V_F (I_F = 50$ MA) < 1.1 B; $C_D < 0.35$ n Φ	SCD-80	K • /
M	BZX584C51-02V	VISH	dz	V _Z (I _{ZT} = 2 mA) = 4854 B; Z _{ZT} < 180 Om	SOD-523, SC-79	
N	BAR65-02V	INF		$V_R < 30 \text{ B; } I_E < 100 \text{ mA; } V_E (I_E = 100 \text{ mA}) < 1.0 \text{ B; } C_D < 0.9 \text{ n} \Phi$	SOD-523, SC-79	
n	BAT15-02V	INF		$V_B < 4B$; $I_F < 100$ mA; $V_F (I_F = 10$ mA) < 0.41 B; $C_D < 0.35$ m Φ	SOD-523, SC-79	
N	BB181	PHIL		$V_B > 30 \text{ B; } I_B (V_B = 30 \text{ B}) < 0.01 \text{ m/s}, C_{0.5B} = 817 \text{ n/b}; C_{28B} = 0.71.055 \text{ n/b}$	SOD-523, SC-79	
N N	BB181	LRC			SOD-523, SC-79	-
0	BAR64-02V	_		V _R >30 B; I _R (V _R =30 B)<0.01 mrA; C _{0.5B} =817 nΦ; C _{28B} =0.71.055 nΦ	SOD-523, SC-79 SOD-523, SC-79	
J		INF	-	V _R <150B; I _F <100 mA; V _F (I _F =50 mA)<1.1 B; C _D <0.35 nΦ	10	
	BZX584C11-02V	VISH	dz	V _Z (I _{ZT} =5mA)=10.411.6B; Z _{ZT} <20 Om	SOD-523, SC-79	
P	BZX584C36-02V	VISH	dz	$V_Z(I_{ZT} = 2 \text{ mA}) = 3438 \text{ B; } Z_{ZT} < 90 \text{ Om}$	SOD-523, SC-79	
R	BZX584C10-02V	VISH	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 9.410.6 \text{ B}; Z_{ZT} < 20 \text{ Om}$	SOD-523, SC-79	
3	BZX584C39-02V	VISH	dz	$V_Z(I_{ZT} = 2 \text{ mA}) = 3741 \text{ B}; Z_{ZT} < 130 \text{ Om}$	SOD-523, SC-79	_
RA	BA895	INF		$V_R > 50 \text{ B}; I_F < 50 \text{ mA}; V_F (I_F = 50 \text{ mA}) < 1.1 \text{ B}; I_R < 0.02 \text{ mKA}$	SCD-80	K•#
RR	BBY59-02V	INF		$V_R < 15 \text{ B}; I_F < 50 \text{ mA}; I_B < 0.02 \text{ mKA}; C_{1B} = 26.629 \text{ n}\Phi; C_{4B} = 6.17.8 \text{ n}\Phi$	SOD-523, SC-79	
S	BAP64-02	PHIL		$V_R > 175B$; $I_F < 100 \text{ mA}$; $V_F (I_F = 50 \text{ mA}) < 1.1 B$; $I_R < 0.1 \text{ mKA}$	SOD-523, SC-79	
S	BZX584C43-02V	VISH	dz	$V_Z(I_{ZT} = 2 \text{ mA}) = 4046 \text{ B}; Z_{ZT} < 150 \text{ Om}$	SOD-523, SC-79	
S		VISH	dz	$V_Z(I_{ZT}=5\text{ mA})=8.59.6\text{ B}; Z_{ZT}<15\text{ Om}$	SOD-523, SC-79	
53	1SS388	TOSH	shd	$V_R < 40 \text{ B}; V_F (I_F = 50 \text{ mA}) < 0.6 \text{ B}; I_R (V_R = 10 \text{ B}) < 5 \text{ mKA}; C_T < 25 \text{ n}\Phi$	SOD-523, SC-79	K•
S4	1SS389	TOSH	shd	$V_R < 10 \text{ B}; V_F (I_F = 100 \text{ mA}) < 0.5 \text{ B}; I_R (V_R = 10 \text{ B}) < 20 \text{ m/sA}; C_T < 40 \text{ n}\Phi$	SOD-523, SC-79	K•A
Т	BAR67-02V	INF	pin	$V_B < 150B$; $I_F < 200 \text{ mA}$; $V_F (I_F = 50 \text{ mA}) < 1.2 B$; $C_D < 0.9 \text{ n}\Phi$	SOD-523, SC-79	K•
Т	BAR67-02W	SIEM	pin	$V_B < 150B$; $I_E < 200 \text{ mA}$; $V_E (I_E = 50 \text{ mA}) < 1.2 B$; $C_D < 0.9 \text{ n}\Phi$	SCD-80	K • A
t	BAT64-02V	INF	shd	$V_B < 40 \text{ B}; I_E < 250 \text{ mA}; V_E (I_E = 100 \text{ mA}) < 0.75 \text{ B}; I_B < 2 \text{ m/cA}; C_D < 6 \text{ n}\Phi$	SOD-523, SC-79	K•A
Т	BZX584C8V2-02V	VISH	dz	$V_7(I_{77}=5\text{mA})=7.78.7\text{ B; }Z_{77}<15\text{ Om}$	SOD-523, SC-79	K•A
T1	1SV278	TOSH	var	$V_B > 30 \text{ B}; I_B (V_B = 28 \text{ B}) < 0.01 \text{ MrA}; C_{2B} = 14.1616.25 \text{ n}\Phi; C_{25B} = 2.112.43 \text{ n}\Phi$	SOD-523, SC-79	K • A
T3	1SV309	TOSH		$V_B > 30 \text{ B}; I_B (V_B = 28 \text{ B}) < 0.01 \text{ m/sA}; C_{2B} = 3.314.55 \text{ n/D}; C_{25B} = 0.610.77 \text{ n/D}$	SOD-523, SC-79	
17	1SV286	TOSH		$V_B > 30 \text{ B}; I_B (V_B = 28 \text{ B}) < 0.01 \text{ mrA}; C_{2B} = 14.516.1 \text{ n}\Phi; C_{20B} = 1.561.86 \text{ n}\Phi$	SOD-523, SC-79	_
18	1SV279	TOSH		V _B > 15 B; I _B (V _B = 15 B)< 0.003 мкА; С _{2B} =1416 пФ; С _{10B} =5.56.5 пФ	SOD-523, SC-79	
TC	1SV280	TOSH		V _B > 15 B; I _B (V _B = 15 B)< 0.003 мкА; С _{2B} = 3.84.7 пФ; С _{10B} = 1.52 пФ	SOD-523, SC-79	
TD	1SV282	TOSH		$V_B > 34 B$, $I_B (V_B = 32 B) < 0.01 MKA; C_{2B} = 3338 \text{ n}\Phi; C_{25B} = 2.63 \text{ n}\Phi$	SOD-523, SC-79	
E	1SV283	TOSH		$V_B > 34 B_1 I_B (V_B = 32 B) < 0.01 \text{ mKA}; C_{2B} = 2934 n\Phi; C25B = 2.52.9 n\Phi$	SOD-523, SC-79	
F	1SV281	TOSH		V _B >10 B; I _B (V _B =10 B)< 0.003 мкA; C _{1 B} =1517 πΦ; C _{4 B} =7.38.7 πΦ	SOD-523, SC-79	
IJ	1SV290	TOSH		$V_B > 30 \text{ B}, I_B (V_B = 28 \text{ B}) < 0.01 \text{ m/s}, C_{2B} = 4149.5 \text{ n/p}, C_{25B} = 2.53.2 \text{ n/p}$	SOD-523, SC-79	-
TK	1SV291	TOSH		$V_B > 30 \text{ B; } I_B (V_B = 28 \text{ B}) < 0.01 \text{ m/sA}; C_{2B} = 4.25.7 \text{n/p}; C_{25B} = 0.530.68 \text{ n/p}$	SOD-523, SC-79	
TL.	1SV284	TOSH		$V_R > 10 \text{ B; } I_R (V_R = 10 \text{ B}) < 0.003 \text{ m/sA; } C_{2B} = 4.25.71 \text{ m/s}; } C_{2B} = 0.33038 \text{ m/s}}$	SOD-523, SC-79	
0	1SV285	TOSH			SOD-523, SC-79	
		_	-	V _R >10 B; I _R (V _R =10B)<0.003 mKA; C _{1B} =44.9 nФ; C _{4B} =1.852.35 nФ		_
П	1SV303	TOSH	var	V _B >30 B; I _B (V _B =28 B)<0.01 мкA; C _{2 B} =4251 πΦ; C _{25 B} =2.13.1 πΦ	SOD-523, SC-79	
TV	1SV305	TOSH	var	V _B > 10 B; I _B (V _B = 10 B)< 0.003 мкА; С _{1 B} =17.319.3 пФ; С _{4 B} =5.36.6 пФ	SOD-523, SC-79	
TX	1SV308	TOSH	-	$V_R > 30 \text{ B; } I_F < 50 \text{ mA; } V_F (I_F = 50 \text{ mA}) < 1 \text{ B; } I_R < 0.1 \text{ m/s}$	SOD-523, SC-79	
ΙΥ	1SS381	TOSH	di	$V_R < 30 \text{ B}; I_F < 100 \text{ mA}; V_F (I_F = 2 \text{ mA}) < 0.85 \text{ B}; I_R < 0.1 \text{ mKA}$	SOD-523, SC-79	
J	BB145	PHIL	var	$V_R > 6B; I_R(V_R = 6B) < 0.01 \text{ m/A}; C_{1B} = 6.47.4 \text{ n}\Phi; C_{4B} = 2.753.25 \text{ n}\Phi$	SOD-523, SC-79	
U	BB145	LRC		$V_B > 6B$; $I_B (V_B = 6B) < 0.01 \text{ mrA}$; $C_{1B} = 6.47.4 \text{ n}\Phi$; $C_{4B} = 2.753.25 \text{ n}\Phi$	SOD-523, SC-79	
V.6	JDV2S10T	TOSH	var	$V_R < 10 B$; $I_R < 0.003 \text{ mKA}$; $C_{0.5B} = 7.38.4 \text{ n}\Phi$; $C_{2.5B} = 2.753.4$	SOD-523, SC-79	K.

- SOD623 SOD723

SOD523 SOD219AB SMF





Код	Типономинал	Б	Φ	Особенности	Корпус	Ц:1•2
V1	1SV311	TOSH	var	$V_B > 10 \text{ B}; I_B (V_B = 10 \text{ B}) < 0.003 \text{ mKA}; C_{1B} = 9.711.1 \text{ n}\Phi; C_{4B} = 4.455.45 \text{ n}\Phi$	SOD-523, SC-79	K∙A
V2	1SV329	TOSH	var	$V_B > 10 B; I_B (V_B = 10 B) < 0.003 mkA; C_{1B} = 5.76.7 n\Phi; C_{4B} = 1.852.45 n\Phi$	SOD-523, SC-79	K•A
V6	1SV314	TOSH	var	$V_B > 10 B$; $I_B (V_B = 10 B) < 0.003 mkA$; $C_{0.5B} = 7.38.4 n\Phi$; $C_{2.5B} = 2.753.4 n\Phi$	SOD-523, SC-79	K•A
٧7	1SV323	TOSH	var	$V_B > 10 \text{ B}; I_B (V_B = 10 \text{ B}) < 0.003 \text{ m/sA}; C_{1B} = 26.529.5 \text{ n}\Phi; C_{4B} = 67.1 \text{ n}\Phi$	SOD-523, SC-79	K•A
V8	1SV325	TOSH	var	$V_B > 10 \text{ B}; I_B (V_B = 10 \text{ B}) < 0.003 \text{ m/sA}; C_{1B} = 4449.5 \text{ n}\Phi; C_{4B} = 9.212 \text{ n}\Phi$	SOD-523, SC-79	K•A
V9	1SV331	TOSH	var	$V_B > 10 B$; $I_B (V_B = 10 B) < 0.003 mkA$; $C_{1B} = 1719 n\Phi$; $C_{4B} = 4.255.43 n\Phi$	SOD-523, SC-79	K•A
W5	GZF3V6C	VISH	dz	$V_Z = 3.43.8 B; Z_{ZT} (I_Z = 100 mA) < 8 Om$	DO-219AB, SMF	K•A
W6	GZF3V9C	VISH	dz	Vz = 3.74.1 B; Zz _T (Iz = 100 mA) < 8 Om	DO-219AB, SMF	K•A
W7	GZF4V3C	VISH	dz	V _Z = 4.04.6 B; Z _{ZT} (I _Z = 100 mA) < 7 Om	DO-219AB, SMF	K•A
8W	GZF4V7C	VISH	dz	Vz = 4.45.0 B; ZzT (Iz = 100 mA) < 7 Om	DO-219AB, SMF	K•A
W9	GZF5V1C	VISH	dz	V _Z =4.85.4 B; Z _{ZT} (I _Z =100 mA) < 6 Om	DO-219AB, SMF	K•A
WA	GZF5V6C	VISH	dz	$V_Z = 5.26.0 \text{ B; } Z_{ZT} (I_Z = 100 \text{ mA}) < 40 \text{ m}$	DO-219AB, SMF	K•A
WB	GZF6V2C	VISH	dz	$V_z = 5.86.6 \text{ B}; Z_{zz} (I_z = 100 \text{ mA}) < 3 \text{ Om}$	DO-219AB, SMF	K•A
WC	GZF6V8C	VISH	dz	V _Z =6.47.2B; Z _{ZT} (I _Z =100 mA)<30m	DO-219AB, SMF	K•A
WD	GZF7V5C	VISH	dz	Vz = 7.07.9 B; ZzT (Iz = 100 mA) < 2 Om	DO-219AB, SMF	K•A
WE	GZF8V2C	VISH	dz	$V_z = 7.78.7 \text{ B}; Z_{ZT}(I_z = 100 \text{ mA}) < 20 \text{ m}$	DO-219AB, SMF	K•A
WF	GZF9V1C	VISH	dz	Vz = 8.59.6 B; ZzT (Iz = 50 mA) < 4 Om	DO-219AB, SMF	K•A
WG	GZF10C	VISH	dz	$V_7 = 9.410.6 \text{ B}; Z_{7T}(I_7 = 50 \text{ mA}) < 40 \text{ m}$	DO-219AB, SMF	K•A
WH	GZF11C	VISH	dz	$V_z = 10.411.6 \text{ B; } Z_{z1}(I_z = 50 \text{ mA}) < 70 \text{ m}$	DO-219AB, SMF	K•A
WI	GZF12C	VISH	dz	$V_z = 11.412.7 \text{ B; } Z_{zz} (I_z = 50 \text{ mA}) < 70 \text{ m}$	DO-219AB, SMF	K•A
WK	GZF13C	VISH	dz	$V_z = 12.414.1 \text{ B; } Z_{zT} (I_z = 50 \text{ mA}) < 10 \text{ Om}$	DO-219AB, SMF	K•A
WL	GZF15C	VISH	dz	$V_2 = 13.815.6 \text{ B; } Z_{21} (I_2 = 50 \text{ mA}) < 10 \text{ Om}$	DO-219AB, SMF	K•A
WM	GZF16C	VISH	dz	$V_2 = 15.317.1 \text{ B; } Z_{27} (I_2 = 25 \text{ mA}) < 150 \text{ m}$	DO-219AB_SMF	K•A
WN	GZF18C	VISH	dz	$V_z = 16.819.1 \text{ B; } Z_{zz} (I_z = 25 \text{ mA}) < 150 \text{ m}$	DO-219AB, SMF	K•A
WO	GZF20C	VISH	dz	$V_z = 18.821.2 \text{ B; } Z_{z1}(I_z = 25 \text{ mA}) < 150 \text{ m}$	DO-219AB, SMF	K•A
WP	GZF22C	VISH	dz	$V_z = 20.823.3 \text{ B; } Z_{zz} (I_z = 25 \text{ mA}) < 150 \text{m}$	DO-219AB, SMF	K•A
WR	GZF24C	VISH	dz	$V_2 = 22.825.6 \text{ B}; Z_{21}(I_2 = 25 \text{ mA}) < 15 \text{ Om}$	DO-219AB, SMF	K•A
WS	GZF27C	VISH	dz	$V_z = 25.128.9 \text{ B; } Z_{zz}(I_z = 25 \text{ mA}) < 150 \text{ m}$	DO-219AB, SMF	K•A
WT	GZF30C	VISH	dz	$V_z = 2832 \text{ B; } Z_{zT} (I_z = 25 \text{ mA}) < 150 \text{ m}$	DO-219AB, SMF	K•A
WU	GZF33C	VISH	dz	$V_z = 3135 \text{ B}; Z_{zz} (I_z = 25 \text{ mA}) < 150 \text{ m}$	DO-219AB, SMF	K•A
ww	GZF36C	VISH	dz	$V_2 = 3438 \text{ B; } Z_{2T} (I_2 = 10 \text{ mA}) < 400 \text{ m}$	DO-219AB, SMF	K•A
WX	GZF39C	VISH	dz	$V_z = 3741 \text{ B; } Z_{zx}(I_z = 10 \text{ mA}) < 400 \text{ m}$	DO-219AB, SMF	K•A
WY	GZF43C	VISH	dz	$V_z = 4046 \text{ B}; Z_{zT}(I_z = 10 \text{ mA}) < 450 \text{ m}$	DO-219AB, SMF	K•A
WZ	GZF47C	VISH	dz	$V_7 = 4450 \text{ B; } Z_{7T} (I_7 = 10 \text{ mA}) < 450 \text{ m}$	DO-219AB, SMF	K•A
χ	BB187	PHIL	var	$V_B > 32 \text{ B; } I_B (V_B = 30 \text{ B}) < 0.01 \text{ m/sA}, C_{2B} = 29.334.2 \text{ n/p}; C_{25B} = 2.572.92 \text{ n/p}$	SOD-523, SC-79	K•A
χ	BB187	LRC	var	$V_B > 32 \text{ B}; I_B (V_B = 30 \text{ B}) < 0.01 \text{ m/sA}; C_{2B} = 29.334.2 \text{ n/p}; C_{25B} = 2.572.92 \text{ n/p}$	SOD-523, SC-79	K•A
Χ1	GZF51C	VISH	dz	$V_z = 4854 \text{ B}; Z_{zT}(I_z = 10 \text{ mA}) < 60 \text{ Om}$	DO-219AB, SMF	K•A
Х2	GZF56C	VISH	dz	$V_z = 5260 \text{ B}; Z_{zT} (I_z = 10 \text{ mA}) < 60 \text{ Om}$	DO-219AB, SMF	K•A
ХЗ	GZF62C	VISH	dz	V _Z = 5866 B; Z _{ZT} (I _Z = 10 mA) < 80 Om	DO-219AB, SMF	K•A
Х4	GZF68C	VISH	dz	$V_7 = 6472 \text{ B; } Z_{2T}(I_7 = 10 \text{ mA}) < 800 \text{ m}$	DO-219AB, SMF	K•A
X5	GZF75C	VISH	dz	$V_7 = 7079 \text{ B; } Z_{77} (I_7 = 10 \text{ mA}) < 100 \text{ Om}$	DO-219AB, SMF	K•A
X6	GZF82C	VISH	dz	$V_7 = 7787 \text{ B}; Z_{27} (I_7 = 10 \text{ mA}) < 100 \text{ Cm}$	DO-219AB, SMF	K•A
Х7	GZF91C	VISH	dz	$V_z = 8596 \text{ B}; Z_{zT} (I_z = 5 \text{ mA}) < 200 \text{ Om}$	DO-219AB, SMF	K•A
у	BAS52-02V	INF	shd	$V_B < 45 \text{ B}; I_E < 750 \text{ mA}; V_E (I_E = 200 \text{ mA}) < 0.6 \text{ B}; I_B < 80 \text{ mkA}; C_D < 10 \text{ n}\Phi$	SOD-523, SC-79	K•A
Υ	BB182B	PHIL		$V_B > 34 B$; $I_B (V_B = 32 B) < 0.01 \text{ mKA}$; $C_{2B} = 4753 \text{ n}\Phi$; $C_{25B} = 2.653 \text{ n}\Phi$	SOD-523, SC-79	K•A
Υ	BB182B	LRC	var	$V_B > 34 B$; $I_B (V_B = 32 B) < 0.01 mKA$; $C_{2B} = 4753 n\Phi$; $C_{25B} = 2.653 n\Phi$	SOD-523, SC-79	K•A
Z	BB145B	PHIL		$V_B > 6B; I_B(V_B = 6B) < 0.01 \text{ MrA}; C_{1B} = 6.47.2 \text{ n}\Phi; C_{4B} = 2.552.95 \text{ n}\Phi$	SOD-523, SC-79	
Z	BB145B	LRC		$V_B > 6B; I_B(V_B = 6B) < 0.01 \text{ MKA}; C_{1B} = 6.47.2 \text{ n}\Phi; C_{4B} = 2.552.95 \text{ n}\Phi$	SOD-523, SC-79	
Z1	BB145B-01	PHIL		$V_B > 6 \text{ B; } I_B (V_B = 6 \text{ B}) < 0.01 \text{ mrA; } C_{1B} = 6.47.2 \text{ n}\Phi; C_{4B} = 2.552.95 \text{ n}\Phi$	SOD-723	K•A



TSLP-3, SOT883







μDFN-6

SOT883, TSLP, µDFN

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1 • 2 • 3
62	BAT62-07L4	INF	shd x2	V_R <40B; I_F <20 mA; V_F (I_F = 2 mA) < 1B; I_R <10 mrA; C_D <0.6 n Φ	TSLP-4	K1 • K2 • A2 • A1
83	BAT68-02L	INF	shd	$V_B < 8B$; $I_E < 130 \text{ mA}$; $V_E (I_E = 10 \text{ mA}) < 0.5B$; $I_B < 0.1 \text{ mkA}$; $C_D < 1.0 \text{ n}\Phi$	TSLP-2	K●A
88	BBY58-02L	INF	var	$V_B < 10B; I_F < 20 \text{ MA}; I_R < 0.01 \text{ MKA}; C_{1B} = 17.519.3 \text{ n}\Phi; C_{4B} = 5.56.6 \text{ n}\Phi$	TSLP-2	K•A
55	BBY57-02L	INF	var	$V_R < 10B$; $I_F < 20$ mA; $I_R < 0.01$ mkA; $C_{1B} = 16.518.6$ n Φ ; $C_{4B} = 3.55.5$ n Φ	TSLP-2	K•A
6A	BAS16-07L4	INF	dix 2	$V_B < 80B$; $I_F < 200 \text{ mA}$; $V_F (I_F = 150 \text{ mA}) < 1.25 B$; $I_B < 50 \text{ mKA}$	TSLP-4	K1 • K2 • A2 • A1
A4	BAV70L3	INF	di x2	V_R <80B; I_R <200 mA; V_F (I_F =50 mA)<1B; I_R (V_R =70 B)<0.15 mkA; C_D <1.5 n Φ ; t_{RR} <4 hc	TSLP-3	A1 • A2 • K1, K2
A6	BAS16-02L	INF	di	$V_R < 80B$; $I_F < 200 \text{ mA}$; $V_F (I_F = 150 \text{ mA}) < 1.25 B$; $I_R < 50 \text{ mKA}$	TSLP-2	K∙A
AA	BA892-02L	INF	dtv	$V_B < 35B$; $I_F < 10 \text{ mA}$; $V_F (I_F = 100 \text{ mA}) < 1.0B$; $I_B < 0.02 \text{ mkA}$	TSLP-2	K•A
AA	MAX4599ELT	MAX	asw	SPDT; R _{DN} < 65 O _M , V _{DD} = 2.05.5 B	μDFN-6	IN • V+• GND • NC • COM • NO
AB	MAX4594ELT	MAX	asw	SPST; R _{ON} < 12 O _M , V ₀₀ = 2.05.5 B	μDFN-6	COM • NO • GND • IN • n.c. • V+
AC	MAX4595ELT	MAX	asw	SPST; R _{ON} < 12 O _M ; V _{DD} = 2.05.5 B	μDFN-6	COM • NC • GND • IN • n.c. • V+
AD	MAX4596ELT	MAX	asw	SPST; R _{ON} < 12 Om, V _{DO} = 2.05.5 B	μDFN-6	IN • COM • GND • NO • n.c. • V+
AE	MAX4597ELT	MAX	asw	SPST; R _{DN} < 12 O _M , V _{DD} = 2.05.5 B	μDFN-6	IN • COM • GND • NC • n.c. • V+
B8	BBY58-07L4	INF	var	$V_B < 10B$; $I_F < 20$ mA; $I_B < 0.01$ mkA; $C_{1B} = 17.519.3$ n Φ ; $C_{4B} = 5.56.6$ n Φ	TSLP-4	K1 • K2 • A2 • A1
D4	BC847AM	PHIL	npn	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} = 110220; f_T > 100 \text{ MFu}$	SOT-883, SC-101	B•E•C
D5	BC847BM	PHIL	npn	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} = 200450; f_T > 100 \text{ MFL}$	SOT-883, SC-101	B•E•C
D6	BC847CM	PHIL	npn	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mB}_T; h_{21} = 200450; f_T > 100 \text{ MFL}$	SOT-883, SC-101	B∙E∙C
DE	PDTA114TM	PHIL	Dpnp	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} > 200; R_1 10 \text{ kOm}$	SOT-883, SC-101	B∙E∙C
DF	PDTA114YM	PHIL	Dpnp	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} > 100; 10 \text{ kOm}/47 \text{ kOm}$	SOT-883, SC-101	B∙E∙C
DH	PDTA124EM	PHIL	Dpnp	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} > 60; 22 \text{ kOm}/22 \text{ kOm}$	SOT-883, SC-101	B∙E∙C
DL	PDTA143EM	PHIL	Dpnp	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} > 30; 4.7 \text{ kOm}/4.7 \text{ kOm}$	SOT-883, SC-101	B•E•C
DN	PDTA143XM	PHIL	Dpnp	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} > 50; 4.7 \text{ kOm}/10 \text{ kOm}$	SOT-883, SC-101	B•E•C
DP	PDTA143ZM	PHIL	Dpnp	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} > 100; 4.7 \text{ kOm}/47 \text{ kOm}$	SOT-883, SC-101	B∙E∙C
DR	PDTA144EM	PHIL	Dpnp	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} > 80; 47 \text{ kOm}/47 \text{ kOm}$	SOT-883, SC-101	B•E•C
DS	PDTC114EM	PHIL	Dnpn	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} > 30; 10 \text{ кOm}/10 \text{ кOm}$	SOT-883, SC-101	B•E•C
DT	PDTC114TM	PHIL	Dnpn	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} > 200; R_1 10 \text{ kOm}$	SOT-883, SC-101	B•E•C
DU	PDTC114YM	PHIL	Dnpn	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} > 100; 10 \text{ kOm}/47 \text{ kOm}$	SOT-883, SC-101	B•E•C
DX	PDTC124EM	PHIL	Dnpn	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} > 60; 22 \text{ kOm}/22 \text{ kOm}$	SOT-883, SC-101	B•E•C
E1	PDTC143EM	PHIL	Dnpn	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} > 30; 4.7 \text{ kOm}/4.7 \text{ kOm}$	SOT-883, SC-101	B•E•C
E2	PDTC143XM	PHIL	Dnpn	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} > 50; 4.7 \text{ kOm}/10 \text{ kOm}$	SOT-883, SC-101	B•E•C
E 3	PDTC143ZM	PHIL	Dnpn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBT; } h_{21} > 100; 4.7 \text{ kOm}/47 \text{ kOm}$	SOT-883, SC-101	B∙E∙C
E7	PDTC144EM	PHIL	Dnpn	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} > 80; 47 \text{ kOm}/47 \text{ kOm}$	SOT-883, SC-101	B•E•C
F	BAS70-02L	INF	shd	$V_R < 70B$; $I_F < 70 \text{ mA}$; $V_F (I_F = 15 \text{ mA}) < 1.0 B$; $I_R < 0.1 \text{ mKA}$, $C_D < 2.0 \text{ n}\Phi$	TSLP-2	K•A
FF	BAS40-02L	INF	shd	$V_R < 40B$; $I_F < 120$ mA; $V_F (I_F = 40$ mA) < 1 B; $I_R < 1.0$ mKA; $C_D < 5$ r/ Φ	TSLP-2	K•A
G	BAR63-02L	INF	pin	$V_R \le 50B$; $I_F \le 100$ mA; $V_F (I_F = 100$ mA) ≤ 1.2 B; $I_R \le 0.01$ mKA	TSLP-2	K•A
II	BBY51-02L	INF	var	V _R <7B; I _F <20 мA; I _R <0.01 мкА; С _{1 В} =5.055.75 пФ; С4V=2.53.7 пФ	TSLP-2	K•A
K	BBY52-02L	INF	var	$V_R < 7 \text{ B}; I_F < 20 \text{ mA}; I_R < 0.01 \text{ mKA}; C_{1B} = 1.42.2 \text{ n}\Phi; C_{4B} = 0.851.45 \text{ n}\Phi$	TSLP-2	K•A
L	BAT62-02L	INF	shd	$V_R < 40B$; $I_F < 20 \text{ mA}$; $V_F (I_F = 2 \text{ mA}) < 1B$; $I_R < 10 \text{ mkA}$; $C_D < 0.6 \text{ n}\Phi$	TSLP-2	K•A
LO	RN1101FS	TOSH	Dnpn	$V_{CED} = 50 \text{ B; } I_C = 150 \text{ mA; } P_D = 100 \text{ mBT; } f_T > 250 \text{ MFu; } R_1/R_2 = 4.7/4.7 \text{ kOm}$	SOT-823	B•E•C



Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
L1	RN1102FS	TOSH	Dnpn	$V_{CED} = 50 \text{ B; } I_C = 150 \text{ mA; } P_D = 100 \text{ mBT; } f_T > 250 \text{MFu; } R_1/R_2 = 10/10 \text{ kOm}$	SOT-823	B•E•C
12	RN1103FS	TOSH	Dnpn	$V_{CE0} = 50 \text{ B; } I_C = 150 \text{ mA; } P_D = 100 \text{ mBT; } f_T > 250 \text{MFu; } R_1/R_2 = 22/22 \text{ kOm}$	SOT-823	B•E•C
L3	RN1104FS	TOSH	Dnpn	$V_{CE0} = 50 \text{ B}; I_C = 150 \text{ mA}; P_D = 100 \text{ mBT}; f_T > 250 \text{MFu}; R_1/R_2 = 47/47 \text{ kOm}$	SOT-823	B•E•C
L4	RN1105FS	TOSH	Dnpn	$V_{CE0} = 50 \text{ B}; I_C = 150 \text{ mA}; P_D = 100 \text{ mBT}; f_T > 250 \text{MFu}; R_1/R_2 = 2.2/47 \text{ kOm}$	SOT-823	B•E•C
L5	RN1106FS	TOSH	Dnpn	$V_{CE0} = 50 \text{ B}; I_C = 150 \text{ mA}; P_D = 100 \text{ mBT}; f_T > 250 \text{MFu}; R_1/R_2 = 4.7/47 \text{ KOM}$	SOT-823	B•E•C
L6	RN1107FS	TOSH	Dnpn	$V_{CE0} = 50 \text{ B}; I_C = 150 \text{ mA}; P_D = 100 \text{ mBT}; f_T > 250 \text{MFu}; R_1/R_2 = 10/47 \text{ kOm}$	SOT-823	B•E•C
L7	RN1108FS	TOSH	Dnpn	$V_{CE0} = 50 \text{ B; } I_C = 150 \text{ mA; } P_D = 100 \text{ mBT; } f_T > 250 \text{MFu; } R_1/R_2 = 22/47 \text{ kOm}$	SOT-823	B•E•C
L8	RN1109FS	TOSH	Dnpn	$V_{CE0} = 50 \text{ B}; I_C = 150 \text{ mA}; P_D = 100 \text{ mBT}; f_T > 250 \text{MFu}; R_1/R_2 = 47/22 \text{ kOm}$	SOT-823	B•E•C
L9	RN1110FS	TOSH	Dnpn	$V_{CE0} = 50 \text{ B}; I_C = 150 \text{ mA}; P_D = 100 \text{ mBT}; f_T > 250 \text{MFu}; R_1 = 4.7 \text{ kOm}$	SOT-823	B•E•C
LF	RN1111FS	TOSH	Dnpn	$V_{CE0} = 50 \text{ B}; I_C = 150 \text{ mA}; P_D = 100 \text{ mBT}; f_T > 250 \text{MFu}; R_1 = 10 \text{ kOm}$	SOT-823	B•E•C
Ш	RN1112FS	TOSH	Dnpn	$V_{CE0} = 50 \text{ B}; I_C = 150 \text{ mA}; P_D = 100 \text{ mBT}; f_T > 250 \text{MFL}; R_1 = 22 \text{ kOm}$	SOT-823	B•E•C
LJ.	RN1113FS	TOSH	Dnpn	$V_{CE0} = 50 \text{ B}; I_C = 150 \text{ mA}; P_D = 100 \text{ mBT}; f_T > 250 \text{MFu}; R_1 = 47 \text{ kOm}$	SOT-823	B•E•C
Ш	BBY53-02L	INF	var	V _B <6B; I _F <20мA; I _B <0.01мкА; С _{1B} =4.85.8 пФ; С _{3B} =1.853.1 пФ	TSLP-2	K∙A
ш	BBY53-03L	INF	var	$V_R \le 6B$; $I_F \le 20$ MA; $I_R \le 0.01$ MKA; $C_{1B} = 4.85.8$ n Φ ; $C_{3B} = 1.853.1$ n Φ	TSLP-3	A • n.c. • K
MM	BAR64-02L	INF	pin	$V_R < 150B$; $I_F < 100 \text{ mA}$; $V_F (I_F = 50 \text{ mA}) < 1.1 B$; $C_D < 0.35 \text{ n}\Phi$	TSLP-2	K•A
NN	BAR65-02L	INF	pin	$V_R < 30 \text{ B}; I_F < 100 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 1.0 \text{ B}; C_D < 0.9 \text{ n}\Phi$	TSLP-2	K∙A
NP	BAT15-02L	INF	shd	$V_R < 4B$; $I_F < 100$ mA; $V_F (I_F = 10$ mA) < 0.41 B; $C_D < 0.35$ n Φ	TSLP-2	K•A
P3s	BAR63-07L4	INF	pin x2	$V_R < 50 \text{ B}; I_F < 100 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 1.2 \text{ B}; I_R < 0.01 \text{ mKA}$	TSLP-4	K1 • K2 • A2 • A
UO	RN2101FS	TOSH	Dpnp	$V_{CB0} = 20B$; $I_C = 50 \text{ mA}$; $P_D = 50 \text{ mBT}$; $R_1/R_2 = 4.7 \text{ kOm}/4.7 \text{ kOm}$	SOT-823	B•E•C
U1	RN2102FS	TOSH	Dpnp	$V_{CB0} = 20B$; $I_C = 50 \text{ mA}$; $P_D = 50 \text{ mBT}$; $R_1/R_2 = 10/10 \text{ kOm}$	SOT-823	B•E•C
U2	RN2103FS	TOSH	Dpnp	$V_{CB0} = 20B$; $I_C = 50 \text{ mA}$; $P_D = 50 \text{ mB}$ T; $R_1/R_2 = 22/22 \text{ kOm}$	SOT-823	B•E•C
U3	RN2104FS	TOSH	Dpnp	$V_{CB0} = 20B$; $I_C = 50$ mA; $P_D = 50$ mBT; $R_1/R_2 = 47/47$ kOm	SOT-823	B•E•C
U4	RN2105FS	TOSH	Dpnp	$V_{CB0} = 20B$; $I_C = 50 \text{ mA}$; $P_D = 50 \text{ mB}$ T; $R_1/R_2 = 2.2/47 \text{ kOm}$	SOT-823	B•E•C
U5	RN2106FS	TOSH	Dpnp	$V_{CB0} = 20B$; $I_C = 50 \text{ mA}$; $P_D = 50 \text{ mB}$ T; $R_1/R_2 = 4.7/47 \text{ kOm}$	SOT-823	B•E•C
U6	RN2107FS	TOSH	Dpnp	$V_{CB0} = 20B$; $I_C = 50 \text{ mA}$; $P_D = 50 \text{ mB} \text{ T}$; $R_1/R_2 = 10/47 \text{ KOm}$	SOT-823	B•E•C
U7	RN2108FS	TOSH	Dpnp	$V_{CB0} = 20B$; $I_C = 50 \text{ mA}$; $P_0 = 50 \text{ mB}$ T; $R_1/R_2 = 22/47 \text{ kOm}$	SOT-823	B•E•C
U8	RN2109FS	TOSH	Dpnp	$V_{CB0} = 20B$; $I_C = 50 \text{ mA}$; $P_D = 50 \text{ mB}$ T; $R_1/R_2 = 47/22 \text{ kOm}$	SOT-823	B•E•C
U9	RN2110FS	TOSH	Dpnp	V _{CB0} = 20B; I _C = 50 mA; P _D = 50 mBT; R ₁ = 4.7 kOm	SOT-823	B•E•C
UF	RN2111FS	TOSH	Dpnp	V _{CB0} = 20B; I _C = 50 mA; P _D = 50 mBT; R ₁ = 10 kOm	SOT-823	B•E•C
UH	RN2112FS	TOSH	Dpnp	V _{CB0} = 20B; I _C = 50 мА; P _D = 50 мВт; R ₁ = 22 кОм	SOT-823	B•E•C
W	RN2113FS	TOSH	Dpnp	$V_{CB0} = 20B$; $I_C = 50$ mA, $P_D = 50$ mBT, $R_1 = 47$ kOm	SOT-823	B•E•C
WC	BCR133L3	INF	Dnpn	$V_{CB0} = 50B$; $I_C = 100 \text{ mA}$; $P_D = 200 \text{ mBT}$; $h_{21} > 30$; $f_T = 130 \text{ MFL}$	TSLP-3	B•E•C
WD	BCR141L3	INF	Dnpn	$V_{CB0} = 50B$; $I_C = 100 \text{ mA}$; $P_D = 200 \text{ mBT}$; $h_{21} > 50$; $f_T > 130 \text{ MFu}$	TSLP-3	B•E•C
WE	BCR148L3	INF	Dnpn	$V_{CB0} = 50B$; $I_C = 70 \text{ mA}$; $P_D = 200 \text{ mB}\tau$; $h_{21} > 70$; $f_T > 100 \text{ MF}\tau$	TSLP-3	B•E•C
WΗ	BCR108L3	INF	Dnpn	$V_{CB0} = 50B$; $I_C = 100 \text{ mA}$; $P_D = 200 \text{ mB}_T$; $h_{21} > 70$; $f_T > 170 \text{M}\Gamma_U$	TSLP-3	B•E•C
WI	BCR158L3	INF	Dpnp	$V_{CB0} = 50B$; $I_C = 70$ mA; $P_D = 250$ mBT; $h_{21} > 70$; $f_T = 100$ MF $_{LL}$	TSLP-3	B•E•C
WJs	BCR135L3	INF	Dnpn	$V_{CB0} = 50B$; $I_C = 100 \text{ mA}$; $P_D = 200 \text{ mBT}$; $h_{21} > 70$; $f_T > 150 \text{MFu}$	TSLP-3	B•E•C
MM	BCR183L3	INF	Dpnp	$V_{CB0} = 50B$; $I_C = 100 \text{ mA}$; $P_D = 250 \text{ mBT}$; $h_{21} > 30$;	TSLP-3	B•E•C
WP	BCR192L3	INF	Dpnp	$V_{CB0} = 50B$; $I_C = 100$ mA; $P_D = 250$ mBT; $h_{21} > 70$; $f_T > 200$ MFL	TSLP-3	B•E•C
WU	BCR162L3	INF	Dpnp	$V_{CB0} = 50B$; $I_C = 100 \text{ mA}$; $P_D = 200 \text{ mB}\text{T}$; $h_{P1} > 20$; $f_T > 200 \text{ M}\Gamma_U$	TSLP-3	B•E•C





SOT23-3, SOT323/523...

Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
-28	PDTA114WU	PHIL	Dono	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ > 60; 47 kOm/22 kOm	SOT323,SC70	B·E·C
-20	PDTC114WU	PHIL	Dnpn	V _{CR0} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ > 60; 47 kOm/22 kOm	SOT323,SC70	B·E·C
3	BC849	MOT	non	V _{GBO} =30 B; I _G =100 мА; P _D =250 мВт; h ₂₁ =200800; f _T >100 МГц	SOT23,SOD23	B·E·C
11	MMBD1501	NS	dl	V _B <180 B; I _E <600 mA; V _E (I _E =200 mA)<1.1 B; C _D <4πΦ	SOT23.SOD23	A·n.c.•K
11	MMBD1501	FAIR	dl	V _B <200 B; I _E =200 mA; V _E (I _E =200 mA)<1.1B; C _D <4πΦ	SOT23.SOD23	A·n.c.·K
13	MMBD1503	NS	dl×2	V _B <180 B; I _E <600 mA; V _E (I _E =200 mA)<1.1 B; C _D <4πΦ	SOT23,SOD23	A1-K2-K1 A2
13	MMBD1503	FAIR	dl×2	V _B <200 B; I _F =200 mA; V _F (I _F =200 mA)<1.1 B; C _D <4 nΦ	SOT23.SOD23	
14	DTA114ECA	ROHM	Dono	V _{CB0} =50B; I _C =100mA; P _D =150mBr; h ₂₁ >30; f _T >250MFu; R ₁ /R ₂ =10/10kOm		
14	MMBD1504	FAIR	dl×2	V _B <200 B; I _F =200 mA; V _F (I _F =200 mA)<1.1 B; C _D <4 nΦ	SOT23 SOD23	
15	DTA124ECA	ROHM	Dpnip	V_{CB0} =50B, $I_{C(max)}$ =100 MA; P_0 =150 MB τ ; h_{21} >56; f_τ >250 MF u ; P_1 /P $_0$ =22/22 xOM	S0T23,S0D23	B·E·C
15	MMBD1505	FAIR	dl×2	V _R <200 B; I _F =200 mA; V _F (I _F =200 mA)<1.1B; C _D <4 nΦ	SOT23,SOD23	K1-K2-A1.A2
22	MMBT4209	NS	onp	V _{CRD} =15B; I _C =50 MA; P _D =300 MBT; h _{Pl} > 35; f _T =850 MFu	SOT23,SOD23	
23	MMBT3646	NS	non	V _{CR0} =40 B; I _C =300 mA; P _D =625 mBr; h ₂₁ > 15	SOT23.SOD23	
24	DTC114ECA	ROHM	Dnon	V _{CR0} =50B; I _C =100mA; P _D =150mBr; h ₂₁ >30; f _T >250MFu; R ₁ /R ₂ =10/10KOm		CONT. (170-70)
24	MMBD1201	FAIR	di	V _B <100 B; I _E <200 MA; V _E (I _E =200 MA)<1 B; C _D <2 mΦ; t _{BB} <3 Hc	SOT23.SOD23	
25	DTC124ECA	ROHM	Dnpn	FV_{CB0}^{-} 50 B; I_{Climat}^{-} 100 MA; P_D^{-} 150 MBT; h_{21} > 56; f_1 > 250 MF μ ; P_1/P_0^{-} 22/22 KOM	S0T23,S0D23	
29	MMBD1401	NS	d	V _R <175 B; I _F <600 mA; V _F (I _F : 200 mA)<1 B; I _R <0.1 mkA; C _D <2 πΦ	SOT23,SOD23	A·n.c.·K
29	MMBD1401	NS	d	V _B <175 B; I _E <600 mA; V _E (I _E =200 mA)<1 B; I _B <0.1 mrA; C _D <2 πΦ	SOT23.SOD23	A·n.c.·K
31	MMBD1402	NS	d	V _B <175 B; I _E <600 мА; V _E (I _E =200 мА)<1 B; I _B <0.1 мкА; С _D <2 пФ	SOT23.SOD23	n.c.·A·K
32	MMBD1403	NS	d×2	V _B <175 B; I _F <600 мА; V _F (I _F =200 мА)<1 B; I _B <0.1 мкА; С _П <2 пФ	SOT23.SOD23	A1-K2-K1 A2
33	MMBD1404	NS	d×2	V _R <175 B; I _F <600 мA; V _F (I _F =200 мA)<1 B; I _R <0.1 мкА; Сп<2 пФ	SOT23,SOD23	to the top in
34	MMBD1405	NS	d×2	V _B <175 B; I _E <600 мА; V _E (I _E =200 мА)<1 B; I _B <0.1 мкА; С _D <2 пФ	SOT23,SOD23	
43	DTA143EE	MOT	Dpnp	V _{CB0} =50 B; I _C =100 MA; P _D =150 MBT; h ₂₁ > 20; f _T > 250 MFU; R ₁ /R ₅ = 4.7/4.7 κCM	SOT416,SC75A	
45	BAS40-05	DIOT	shd×2	V _R <40B; I _E <200 мA; V _E (I _E =40 мA)<1.0B; I _B <0.2 мкA; C _D <5.0 пФ; t _{BB} <5нс	SOT23.SOD23	A1 · A2 · K2.K1
45	BAS40-05	MCS	shd-2	111 111 111 111		
45	BAS40-05	TSC	shd×2			A1-A2-K2.K1
45	BAS40-05	GS	shd×2	V _R <40B; I _E <200 mA; V _E (I _E =40 mA)<1.0B; I _B <0.2 mkA; C _D <5.0 nΦ; t _{BB} <5 HC	SOT23.SOD23	Description of the second
46	BAS40-06	DIOT	shd×2	V _R <40B; I _E <200 mA; V _E (I _E =40 mA)<1.0B; I _B <0.2 mkA; C _D <5.0 nΦ; t _{BB} <5 hc	SOT23,SOD23	
46	BAS40-06	MCS	shd×2	V _R <40B; I _E <200 mA; V _E (I _E =40 mA)<1.0B; I _B <0.2 mkA; C _D <5.0 nΦ; t _{BB} <5 hc	SOT23,SOD23	
16	BAS40-06	TSC	shd×2	V _B <40B; I _E <200 мA; V _E (I _E =40 мA)<1.0B; I _B <0.2 мкA; C _D <5.0 пФ; t _{BB} <5нс	SOT23,SOD23	
46	BAS40-06	GS	shd×2	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1		
69	DTA114YE	MOT	Dono	V _{CRO} =50B; I _C =100 MA; P _D =150 MBT; h ₂₁ >68; f _T >250 MFU; R ₁ /R ₂ =10/47 KOM		
69	DTC115EE	ROHM	Dnpn	V _{CB0} =50 Bi, I _{C(max)} =100 mA; P _D =150 mBT; h ₂₁ >82; f _T >250 MFu; R ₁ /R ₂ =100/100 kOm	SOT416,SC75A	
69	DTC115EUA	ROHM	Dnpn	V_{CB0} =50B; I_0 =30MA; P_0 =200MBT; I_{12} >82; f_7 >250MFu; I_{13} R ₁ /R ₂ =100/100 kOM	SOT323,SC70	B.E.C
72	2N7002	SIL	nFET	V _{ns} =60B; I _n =115 мА; P _n =300 мВт; V _{esth} =12.5B; C _{iss} <50 пФ	SOT23,SOD23	G·S·D
73	MA4CS101A	M/A	shd	V _R -70B; I _E <15 MA; V _E (I _E -15 MA)<1B; C _D <2 πΦ	SOT23,SOD23	A·n.c.·K
74	MA4CS101B	M/A	shd×2	V _R =70B; I _E <15 MA; V _E (I _E =15 MA)<1B; C _D <2 nΦ	SOT23,SOD23	A1-K2-K1,A2
78	MMBT4258	FAIR	pnp	V _{CB0} =12 B; I _C =200 mA; P _D =225 mBT; h ₂₁ =30120; f _T >700 MF _U	SOT23,SOD23	B-E-C
33	MA4CS102A	M/A	shd	V _B =8 B; I _E <30 mA; V _E (I _E =10 mA)<500 mB; C _D <1 πΦ	SOT23,SOD23	
33	MMBT4400	FAIR	non	V _{CR0} =60 B; I _C =1 A; P _D =350 MBT; h ₂₁ =50150	SOT23,SOD23	
84	MA4CS102B	M/A	shd×2	V _n =8 B; I _n <30 mA; V _n (I _n =10 mA) <500 mB; C _n <1 nΦ	SOT23,SOD23	
35	MA4CS102C	M/A	shd×2	V _R =8 B; I _E <30 mA; V _E (I _E =10 mA)<500 mB; C _D <1 nΦ	SOT23.SOD23	
35	MMBD1701	FAIR	d	V _R <30B; I _E =50 мA; V _E (I _E =50 мA)<1.1B; C _D <1 лФ; t _{BB} <0.7 нс	SOT23.SOD23	
86	MMBD1702	FAIR	di	V _B <30B; I _C =50 MA; V _C (I _C =50 MA)<1.1B; C _D <1 nΦ; I _{DB} <0.7 HC	SOT23.SOD23	

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
B7	MMBD1703	FAIR	dk2	$V_R \le 30 B$; $I_F = 50 \text{ mA}$; $V_F (I_F = 50 \text{ mA}) \le 1.1 B$; $C_D \le 1 \text{ m}\Phi$; $t_{RR} \le 0.7 \text{ Hz}$	SOT23,SOD23	A1-K2-K1,A2
88	MMBD1704	FAIR	dlv2	$V_R \le 30 B$; $I_F = 50 mA$; $V_E (I_F = 50 mA) \le 1.1 B$; $C_D \le 1 m\Phi$; $t_{BR} \le 0.7 mc$	SOT23,SOD23	A1+A2+K1,K2
89	MMBD1705	FAIR	dl×2	$V_R < 30B$; $I_F = 50 \text{ mA}$; $V_F (I_F = 50 \text{ mA}) < 1.1B$; $C_D < 1 \text{ mP}$; $t_{RR} < 0.7 \text{ Hz}$	SOT23,SOD23	K1 · K2 · A1, A2
91	DTA113TKA	ROHM	Dpnp	V_{C80} =50 B; I_C =100 mA; P_D =200 mBt; h_{21} >33; f_T >250 MFu; R_1 1 K	SOT346,SC59	B-E-C
95	DTA124TCA	ROHM	Dpnp	V_{C80} =50 B; I_C =100 mA; P_D =150 mBt; h_{21} =100600; f_T >250 MFu; R_1 =22 kOm	SOT23,SOD23	B·E·C
101	PZM10NB1	PHIL	dz	$V_2(I_{ZT}=5 \text{ mA})=9.459.87 \text{ B; } Z_{ZT}(I_{ZT}=5 \text{ mA}) \le 10 \text{ Om}$	SOT346,SC59	A·n.c.·K
102	PZM 10NB2	PHIL	dz	$V_z(I_{ZT}=5 \text{ mA})=9.7710.21 \text{ B; } Z_{ZT}(I_{ZT}=5 \text{ mA})<100 \text{ m}$	SOT346,SC59	A·n.c.·K
103	PZM 10NB3	PHIL	dz	V ₂ (I ₂₇ =5 mA)=10.1110.55B; Z ₂₇ (I ₂₇ =5 mA)<100m	SOT346,SC59	A·n.c.·K
111	PZM11NB1	PHIL	dz	V ₂ (I ₇₁ =5 mA)= 10.4410.88 B; Z ₇₁ (I ₇₁ =5 mA)< 10 Om	SOT346,SC59	A·n.c.·K
112	PZM11NB2	PHIL	dz	V ₂ (I _{ZT} =5 mA)=10.7611.22 B; Z _{ZT} (I _{ZT} =5 mA)<10 0m	SOT346,SC59	A·n.c.·K
113	PZM11NB3	PHIL	dz	V ₂ (I _{ZT} =5 mA)=11.1011.56B; Z _{ZT} (I _{ZT} =5 mA)<100m	SOT346,SC59	
121	PZM12NB1	PHIL	dz	V ₂ (I _{ZT} =5 mÅ)=11.4211.90 B; Z _{ZT} (I _{ZT} =5 mÅ)<10 Om	SOT346,SC59	A·n.c.·K
122	PZM12NB2	PHIL	dz	V ₂ (I _{ZT} =5 mA)=11.7412.24B; Z _{ZT} (I _{ZT} =5 mA)<10 0 m	SOT346.SC59	
123	PZM12NB3	PHIL	dz	V ₂ (I ₂₇ =5 mA)=12.0812.60 B; Z ₂₇ (I ₂₇ =5 mA)<10 0m	SOT346.SC59	10110000010000
131	PZM13NB1	PHIL	dz	V _Z (I _{ZT} =5 mA)= 12.4713.03B; Z _{ZT} (I _{ZT} =5 mA)< 10 Om	SOT346,SC59	100-00-00-00-00-00-00-00-00-00-00-00-00-
132	PZM 13NB2	PHIL	dz	V ₂ (I _{2T} =5 mA)= 12.9113.49 B; Z _{2T} (I _{2T} =5 mA)< 10 0m	SOT346,SC59	
133	PZM13NB3	PHIL	dz	V ₂ (I _{2T} =5 mA)=13.3713.96B; Z _{2T} (I _{2T} =5 mA)<10 Om	SOT346,SC59	
142	DTA123JUA	ROHM	Dnpn	V_{O80} =50 B; I_C =100 mA; P_D =200 mBT; h_{21} >80; f_T >250 MFu;	SOT323,SC70	
151	PZM15NB1	PHIL	dz	R ₁ /R ₂ =2.2/47 KOM V ₂ (I _{2T} =5 MA)= 13.8414.46B; Z _{2T} (I _{2T} =5 MA)< 15 OM	SOT346,SC59	A·n.c.·K
152	PZM 15NB2	PHIL	dz	$V_2(I_{77}=5 \text{ mA})=14.3414.98 \text{ B; } Z_{27}(I_{77}=5 \text{ mA})<150 \text{ m}$	SOT346,SC59	A·n.c.·K
153	PZM15NB3	PHIL	dz	V ₂ (I _{ZT} =5 mA)=14.8515.52B; Z _{ZT} (I _{ZT} =5 mA)<15 Om	SOT346.SC59	
161	PZM16NB1	PHIL	dz	V ₂ (I ₂₇ =5 mA)=15.3716.01B; Z ₂₇ (I ₂₇ =5 mA)<200m	SOT346.SC59	No. 100 (100 (100 (100 (100 (100 (100 (100
162	PZM 16NB2	PHIL	dz	V _Z (I _{ZI} =5 mA)=15.8516.51 B; Z _{ZI} (I _{ZI} =5 mA) < 20 Om	SOT346,SC59	
163	PZM 16NB3	PHIL	dz	V ₂ (I _{ZT} =5 mA)=16.3517.09B; Z _{ZT} (I _{ZT} =5 mA)<200m	SOT346,SC59	
181	PZM 18NB1	PHIL	dz	V ₂ (I _{2T} =5 mA)=16.9417.70B; Z ₂₇ (I _{2T} =5 mA)< 200m	SOT346,SC59	
182	PZM 18NB2	PHIL	dz	V ₂ (I _{2T} =5 mA)=17.5618.35B; Z ₂ (I _{2T} =5 mA)<200m	SOT346.SC59	0.0000000000000000000000000000000000000
183	PZM 18NB3	PHIL	dz	V ₂ (I _{2T} =5 mA)=18.2119.03B; Z ₂ (I _{2T} =5 mA)<200m	SOT346.SC59	100110000000000000000000000000000000000
201	PZM20NB1	PHIL	dz	$V_2(I_{ZT}=5 \text{ mA})=18.8619.70 \text{ B; } Z_{ZT}(I_{ZT}=5 \text{ mA})<200 \text{ m}$	SOT346,SC59	100-000-000-000-000-000-000-000-000-000
202	PZM20NB2	PHIL	dz	V ₂ (I _{2T} =5 mA)=19.5220.39B; Z _{2T} (I _{2T} =5 mA)<200m	SOT346,SC59	
203	PZM20NB3	PHIL	dz	$V_{2}(I_{ZT}-5mA)=20.2121.08B; Z_{ZT}(I_{ZT}-5mA)<200m$	SOT346,SC59	
221	PZM22NB1	PHIL	dz	$V_2(I_{ZT}-5mA)=20.8821.77 B; Z_{ZT}(I_{ZT}-5mA)<250m$	SOT346,SC59	
222	PZM22NB1 PZM22NB2	PHIL	dz	V ₂ (I ₂₇ -5 mA)-20.6621.71 B, Z ₂ (I ₂₇ -5 mA)-25 OM V ₂ (I ₂₇ -5 mA)-21.5422.47 B; Z ₂ (I ₂₇ -5 mA)-25 OM	SOT346,SC59	
223	PZM22NB3	PHIL	dz	$V_2(I_{27}-5 \text{ mA}) = 22.2323.17 \text{ B; } Z_{27}(I_{27}-5 \text{ mA}) = 25.0 \text{ m}$	SOT346,SC59	1200000000000000000
241	PZM24NB1	PHIL	dz		SOT346,SC59	100000000000000000000000000000000000000
242	PZM24NB1 PZM24NB2	PHIL	dz	V _Z (I _{ZT} =5 MA)= 22.9323.96 B; Z _{ZT} (I _{ZT} =5 MA)< 30 Om	SOT346,SC59	
242	PZM24NB2 PZM24NB3	PHIL	dz	V _Z (I _{ZT} =5 mA)= 23.7224.78 B; Z _{ZT} (I _{ZT} =5 mA)< 30 Om	SOT346,SC59	
271		PHIL		V _Z (I _{ZT} =5 MA)=24.5425.57 B; Z _{ZT} (I _{ZT} =5 MA)<30 OM	-	
272	PZM2.7NB1	PHIL	dz	V _Z (I _{ZT} =5 MA) = 2.52.75 B; Z _{ZT} (I _{ZT} =5 MA) < 100 OM	SOT346,SC59	
	PZM2.7NB2	100000	dz	V _Z (I _{ZT} =5 MA)=2.652.9 B; Z _{ZT} (I _{ZT} =5 MA) < 100 Om	SOT346,SC59	100000000000000000000000000000000000000
301	PZM3.0NB1	PHIL	dz	V _Z (I _{ZT} =5 mA) = 2.83.05 B; Z _{ZT} (I _{ZT} =5 mA) < 95 Om	SOT346,SC59	100000000000000000000000000000000000000
302	PZM3.0NB2	PHIL	dz	V _Z (I _{ZT} =5 MA)=2.953.2 B; Z _{ZT} (I _{ZT} =5 MA) < 95 OM	SOT346,SC59	
331	PZM3.3NB1	PHIL	dz	V _Z (I _{ZT} =5 mA)=3.13.35 B; Z _{ZT} (I _{ZT} =5 mA) < 95 Om	SOT346,SC59	
332	PZM3.3NB2	PHIL	dz	V _Z (I _{ZT} =5 mA)=3.253.5 B; Z _{ZT} (I _{ZT} =5 mA) < 95 Om	SOT346,SC59	
358	FDN358P	FAIR		V _{DS} =-30B; I _D =1.5A; P _D =500 mBr; R _{DS(on)} =0.125 Om	SOT23,SOD23	0.000
361	PZM3.6NB1	PHIL	dz	V _Z (I _{ZT} =5 MA) = 3.43.65 B; Z _{ZT} (I _{ZT} =5 MA) < 90 OM	SOT346,SC59	
362	PZM3.6NB2	PHIL	dz	V _Z (I _{ZT} =5 mA)=3.553.8 B; Z _{ZT} (I _{ZT} =5 mA) < 90 Om	SOT346,SC59	121 D. W. P. S. V. V.
391	PZM3.9NB1	PHIL	dz	$V_Z(I_{ZT}=5 \text{ mA})=3.73.97 \text{ B}; Z_{ZT}(I_{ZT}=5 \text{ mA}) < 90 \text{ Om}$	SOT346,SC59	
392	PZM3.9NB2	PHIL	dz	$V_2(I_{ZT}=5 \text{ mA})=3.874.1 \text{ B; } Z_{ZT}(I_{ZT}=5 \text{ mA}) < 90 \text{ Om}$	SOT346,SC59	
431	PZM4.3NB1	PHIL	dz	V _Z (I _{ZT} =5 mA)=4.014.21 B; Z _{ZT} (I _{ZT} =5 mA) < 90 Om	SOT346,SC59	
432	PZM4.3NB2	PHIL	dz	V _Z (I _{ZT} =5 mA)=4.154.34 B; Z _{ZT} (I _{ZT} =5 mA)<90 Om	SOT346,SC59	
433	PZM4.3NB3	PHIL	dz	$V_Z(I_{ZT}=5 \text{ mA})=4.284.48 \text{ B}; Z_{ZT}(I_{ZT}=5 \text{ mA}) \le 90 \text{ Om}$	SOT346,SC59	
471	PZM4.7NB1	PHIL	dz	V _Z (I _{ZT} =5 mA)=4.424.61 B; Z _{ZT} (I _{ZT} =5 mA) < 80 Om	SOT346,SC59	A·n.c.·K





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
472	PZM4.7NB2	PHIL	dz	V _Z (I _{ZT} =5 MA)=4.554.75 B; Z _{ZT} (I _{ZT} =5 MA) < 80 OM	SOT346,SC59	A·n.c.·K
173	PZM4.7NB3	PHIL	dz	V ₂ (I _{ZT} =5 mA)=4.694.90 B; Z _{ZT} (I _{ZT} =5 mA) < 80 Om	SOT346,SC59	A+n.c.+K
500	SSTPAD500	SIL	dl	$V_B = 55B$; $I_E < 10 \text{ MA}$; $V_E (I_E = 1 \text{ MA}) < 1.5 B$; $I_B < 500 \text{ nA}$; $C_T < 2 \text{ n}\Phi$	SOT23,SOD23	K·K·A
511	PZM5.1NB1	PHIL	dz	V ₂ (I ₂₇ =5 mA)=4.845.04 B; Z ₂₇ (I ₂₇ =5 mA) < 60 Om	SOT346,SC59	A+n.c.+K
512	PZM5.1NB2	PHIL	dz	V ₂ (I ₂₁ =5 mA)=4.985.20 B; Z ₂₁ (I ₂₁ =5 mA) < 60 Om	SOT346,SC59	A+n.c.+K
513	PZM5.1NB3	PHIL	dz	V ₂ (I ₂₁ =5 mA)=5.145.37 B; Z ₂₁ (I ₂₁ =5 mA) < 60 Om	SOT346,SC59	A·n.c.·K
561	PZM5.6NB1	PHIL	dz	V ₇ (I ₇₇ =5 MA)=5.315.55 B; Z ₇₇ (I ₇₇ =5 MA) < 40 Om	SOT346,SC59	A·n.c.·K
562	PZM5.6NB2	PHIL	dz	V ₇ (I ₇₇ =5 mA)=5.495.73 B; Z ₇₇ (I ₇₇ =5 mA) < 40 Om	SOT346,SC59	A·n.c.·K
563	PZM5.6NB3	PHIL	dz	V _A (I _{ZT} =5 mA)=5.675.92 B; Z _{ZT} (I _{ZT} =5 mA) < 40 Om	SOT346,SC59	A·n.c.·K
605	NDS0605	FAIR	oMOS	V _{DS} =60B; I _D =180 MA; P _D =360 MBT; R _{DS(on)} <15 OM	SOT23.SOD23	
610	NDS0610	FAIR	oMOS	V _{DS} =60B; I _D =120 мА; P _D =360 мВт; R _{DS(on)} <300 м	SOT23.SOD23	
621	PZM6.2NB1	PHIL	dz	V _Z (I _{ZT} =5 MA)=5.866.12 B; Z _{ZT} (I _{ZT} =5 MA) < 10 OM	SOT346,SC59	
622	PZM6.2NB2	PHIL	dz	V _Z (I _{ZT} =5 mA)=6.066.33 B; Z _{ZT} (I _{ZT} =5 mA) < 10 Om	SOT346.SC59	
623	PZM6.2NB3	PHIL	dz	V _x (I _{zz} =5 mA)=6.266.53 B; Z _{zz} (I _{zz} =5 mA) < 10 Om	SOT346.SC59	100000000000000000000000000000000000000
634	FMMT634	ZETEX	dnpn	V _{CR0} =120B; I _C =900 мA; P ₀ =625 мBт; f _T > 140 MFu	SOT23,SOD23	DEC-38 300 COM
681	PZM6.8NB1	PHIL	dz	V _A (I ₇₇ =5 mA)=6.476.73 B; Z ₂₇ (I ₇₇ =5 mA)<150m	SOT346,SC59	
682	PZM6.8NB2	PHIL	dz	V ₂ (I ₂₇ =5 mA)=6.867.14 B; Z ₂₇ (I ₂₇ =5 mA) < 150m	SOT346,SC59	
683	PZM6.8NB1	PHIL	dz	V _X (₂₇ =5 mA)=6.656.93 B; Z ₂₇ (₁₂₇ =5 mA)<150m	SOT346,SC59	100000000000000000000000000000000000000
701	2N7001	MOT		Pn=250 MBT; V _{BDDSS} >240 B; R _{DS(m1} =450 M	SOT23.SOD23	10.000000000000000000000000000000000000
702	2N7001 2N7002	ON	nFET	V _{DS} =60B; I _D =115 мA; P _D =300мВт; V _{GSTH} =12.5B; C _{ISS} <50 пФ	SOT23,SOD23	F-17
702	2N7002 2N7003	MOT	nFET	V _{DS} =500 B; I _D =115 MA; P _D =300 MB1; V _{GSTH} =12.3 B; C _{ISS} <50 Hp V _{DS} =500 B; I _D =10 MA; P _D =200 MB1; R _{ISS(m)} <300 OM	SOT23,SOD23	108.000 30
712	NDS7002A	NS	nMOS	00 00(m)	SOT23,SOD23	
751	PZM7.5NB1	PHIL		V _{0S} -60B; I ₀ -0.28 A	SOT346,SC59	
752		PHIL	dz	V _Z (I _{ZT} =5 MA)=7.067.36 B; Z _{ZT} (I _{ZT} =5 MA) < 10 OM		
	PZM7.5NB2	PHIL	dz	V _Z (I _{ZT} =5 mA)=7.287.60 B; Z _{ZT} (I _{ZT} =5 mA) < 10 Om	SOT346,SC59	
753	PZM7.5NB3		dz	V _Z (I _{ZT} =5 mA)=7.527.84 B; Z _{ZT} (I _{ZT} =5 mA)<100m	SOT346,SC59	
821	PZM8.2NB1	PHIL	dz	V _Z (I _{ZT} =5 mA)=7.768.10 B; Z _{ZT} (I _{ZT} =5 mA) < 10 0m	SOT346,SC59	101,000,000,000
822	PZM8.2NB2	PHIL	dz	$V_Z(I_{ZT}=5 \text{ mA})=8.028.36 \text{ B; } Z_{ZT}(I_{ZT}=5 \text{ mA}) \le 100 \text{m}$	SOT346,SC59	
823	PZM8.2NB3	PHIL	dz	V _Z (I _{Z1} =5 MA)=8.288.64 B; Z _{Z1} (I _{Z1} =5 MA) < 10 OM	SOT346,SC59	
852	S852T	VISH	npn	V _{CB0} =12B; I _C =8mA; P _D =30mBT; h ₂₁ =40150; f _T =5.2 ГГц	SOT23,SOD23	
911	PZM9.1NB1	PHIL	dz	V _Z (I _{ZT} =5 mA)=8.568.93 B; Z _{ZT} (I _{ZT} =5 mA) < 10 Om	SOT346,SC59	
912	PZM9.1NB2	PHIL	dz	V _Z (I _{ZT} =5 mA)=8.859.23 B; Z _{Z1} (I _{ZT} =5 mA)<10 Om	SOT346,SC59	100000000000000000000000000000000000000
913	PZM9.1NB3	PHIL	dz	V _Z (I _{ZT} =5 mA)=9.159.55 B; Z _{ZT} (I _{ZT} =5 mA) < 10 Om	SOT346,SC59	100000000000000000000000000000000000000
01	PDTA143EE	PHIL	Dpnp	V _{GB0} =50 B; I _G = 100 мA; P _D =250 мВт; h ₂₁ > 30; 4.7 кОм/4.7 кОм	SOT416,SC75A	0.000
01	PDTA143EK	PHIL	Dpnp	V _{CB0} =50 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ > 30; 4.7 кОм/4.7 кОм	SOT346,SC59	
010	SSTPAD10	SIL	dl	V_R =55B; I_F <10 MA; V_F (I_F =1 MA)<1.5B; I_R <10 nA; C_T <2 n Φ	SOT23,SOD23	
011	S02369R	STM	npn	V _{CB0} =40 B; I _C =200 мА; P _D =200 мВт; h ₂₁ =40120; f _T >400 МГц	SOT23,SOD23	
02	DTC123TKA	ROHM	Dnpn	V_{CB0} = 50 B; I_{0} = 100 mA; P_{0} = 200 mBT; h_{21} > 80; f_{7} > 250 MFu; R_{1}/R_{2} = 2.2/47 kOm	SOT346,SC59	B·E·C
02	PDTC143EE	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 мА; P _D =250 мВт; h ₂₁ >30; 4.7 кОм/4.7 кОм	SOT416,SC75A	
02	PDTC143EK	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 мA; P ₀ =250 мВт; h ₂₁ >30; 4.7 кОм/4.7 кОм	SOT346,SC59	B·E·C
020	SSTPAD20	SL	dl	$V_R = 55B$; $I_F \le 10 \text{ mA}$; $V_F (I_F = 1 \text{ mA}) \le 1.5 B$; $I_R \le 20 \text{ nA}$; $C_T \le 2 \text{ n}\Phi$	SOT23,SOD23	K·K·A
028	S03572R	SGS	npn	V _{CB0} =15B; P _D =200 мВт; f _T >1 ГГц	SOT23,SOD23	E·B·C
02p	BST82	PHIL	nMOS	V _{DS} =80B; I _D =175 mA; P _D =300 mBT; R _{DS(on)} =7 Om	SOT23,SOD23	G·S·D
03	DTC143TE	ROHM	Dnpn	V_{CB0} =50 B; I_{C} =100 mA; P_{D} =150 mB;; I_{D1} =100600; f_{T} >250 MFu; R_{1} =4.7 kOm	S0T416,SC75A	B·E·C
03	DTC143TKA	ROHM	Dnpn	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBT; h_{21} =100600; f_T >250 MFu; B_1 =4.7 kOm	S0T346,SC59	B-E-C
03	DTC143TUA	ROHM	Dnpn	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; h_{21} = 100600; f_T > 250 MFu; B_1 = 4.7 kO m	S0T323,SC70	B·E·C
03	PDTA114EE	PHIL	Dpnp	V _{CBD} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ > 30; 10 kOm/10 kOm	SOT416,SC75A	B·E·C
03	PDTA114EEF	PHIL	Dpnp	V _{CR0} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >30; 10 kOm/10 kOm	SOT490,SC89	100000000
-03	PDTA114EU	PHIL	Dpnp	V _{CR0} =50B; I _C =100mA; P _D =200mBT; h ₂₁ >30; 10xOm/10xOm	SOT323,SC70	
03W	S02907AW	STM	pnp	V _{CPD} =60 B; I _C =600 MA; P _D =200 MBT; h ₂₁ =100300; f _T >200 MFц	S0T323,SC70	

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
04	DTC114TE	ROHM	Dnpn	V _{CB0} =50B; I _C =100 MA; P _D =150 MBr; h ₂₁ >100600; f _T >250 MFu; B ₁ =10 xCm	SOT416,SC75A	B-E-C
04	DTC114TKA	ROHM	Dnpn	V_{C80} = 50 B; I_C = 100 mA; P_D = 200 mB τ ; h_{21} > 100600; f_T > 250 MF u ; P_D = 10 xCm	SOT346,SC59	B-E-C
04	DTC114TUA	ROHM	Dnpn	V_{C80}^{-} :50 B; I_C :100 xA; P_D :200 xBr; h_{21} >100600; f_T >250 MFu; P_D :10 xOx	SOT323,SC70	B-E-C
04	PDTC114EK	PHIL	Dnpn	V _{CB0} =50B; I _C =100 MA; P _D =250 MBT; h ₂₁ >30; 10 kOM/10 kOM	SOT346,SC59	B-E-C
-04	PMSS3904	PHIL	npn	V _{C80} =60 B; I _C =200 мA; P _D =200 мВт; h ₂₁ =100300; f _T > 180 МГц	SOT323,SC70	B·E·C
04	DTC114TCA	ROHM	Dnpn	V_{CS0} =50 B; I_C = 100 mA; P_0 = 150 mBT; h_{21} > 100600; f_T > 250 MFu; P_1 = 10 xOm	SOT23,SOD23	B-E-C
044	S03571R	SGS	npn	V_{C80} =15B; P_0 =200 MBT; f_T >1.2 ГГц	SOT23,SOD23	E·B·C
047	SO3570R	SGS	npn	V _{CB0} =15B; P _D =200 мВт; f _T >1.5 ГГц	SOT23,SOD23	E-B-C
05	DTC124TE	ROHM	Dnpn	V_{C80} =50 B; I_C =100 mA; P_D =150 mBt; h_{21} =100600; f_T >250 MFu; R_1 =22 kOm	SOT416,SC75A	B-E-C
05	DTC124TKA	ROHM	Dnpn	V_{C80} =50 B; I_C =100 mA; P_0 =200 mBr; h_{21} =100600; f_T >250 MFu; R_1 =22 kOm	SOT346,SC59	B·E·C
05	DTC124TUA	ROHM	Dnpn	V _{CB0} =50 B; I _C =100 мA; P _D =200 мВт; h ₂₁ =100600; f _T >250 МГц; R ₁ =22 кОм	SOT323,SC70	B•E•C
05	PDTA124EE	PHIL	Dpnp	V _{CB0} =50 B; I _C =100 mA; P _D =250 mBt; h ₂₁ >60; 22 kOm/22 kOm	SOT416,SC75A	B-E-C
05	PDTA124EK	PHIL	Dpnp	V _{CBO} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ >60; 22 кОм/22 кОм	SOT346,SC59	B-E-C
05	SSTPAD5	SIL	dl	V _B =55B; I _E <10mA; V _E (I _E =1mA)<1.5B; I _B <5 nA; C _T <2 nΦ	SOT23,SOD23	K•K•A
050	SSTPAD50	SIL	dl	V ₀ =55B; I _E <10mA; V _E (I _E =1mA)<1.5B; I _B <50πA; C _T <2πΦ	SOT23,SOD23	K•K•A
06	DTC144TE	ROHM	Dnon	V _{CB0} =50B; I _C =100 мA; P _D =150 мВт; h ₂₁ =100600; f _T >250 МГц; R ₁ =47 кОм	SOT416.SC75A	B-E-C
06	DTC144TKA	ROHM	Dnon	V _{C80} =50 B; I _C =100 mA; P ₀ =200 mBr; h ₂₁ =100600; f _T >250 MFu; R₁=47 κOm		
06	DTC144TUA	ROHM	Dnon	V _{G80} =50 B; I _G =100 mA; P _D =200 mBr; h ₂₁ =100600; f _T >250 MFu; R ₁ =47 kOm	SOT323.SC70	
06	PDTC124EE	PHIL	Dnon	V _{CRO} =50 B; I _C =100 mA; P _D =250 mBT; h ₂₁ >60; 22 kOm/22 kOm	SOT416.SC75A	
06	PDTC124EK	PHIL	Dnon	V _{CBD} =50 B; I _C =100 mA; P _D =250 mBT; h ₂₁ >60; 22 kOm/22 kOm	SOT346 SC59	
17	PDTA144FE	PHIL	Dono	V _{CR0} =50 B; I _C =100 MA; P _D =250 MBr; h ₂₁ >80; 47 KOM/47 KOM	SOT416.SC75A	20202
07	PDTA144EEF	PHIL	Dono	V _{C80} =50 B; I _C =100 MA; P _D =250 MB; H ₂₁ >80; 47 KOM/47 KOM	SOT490.SC89	ESSE 5
07	PDTA144EK	PHIL	Dpnp	V _{C80} =50 B; I _C =100 MA; P _D =250 MB; H ₂₁ >80; 47 KOM/47 KOM	SOT346.SC59	100000
08	PDTC144EE	PHIL			SOT416.SC75A	
			Dnpn	V _{C80} =50 B; I _C =100 mA; P _D =250 mBr; h ₂₁ >80; 47 κOm/47 κOm	-	
08	PDTC144EEF	PHIL	Dnpn	V _{G80} =50 B; I _G =100 мA; P _D =250 мBт; h ₂₁ >80; 47 кОм/47 кОм	SOT490,SC89	
08	PDTC144EK	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 мА; P ₀ =250 мВт; h ₂₁ >80; 47 кОм/47 кОм	SOT346,SC59	
081	SO2369AR	SGS	npn	V _{CB0} =40 B; I _C =200 мA; P _D =200 мВт; h ₂₁ =40120; f _T >500 МГц	SOT23,SOD23	2000000
)9	DTC115TH	ROHM	Dnpn	V_{C80} =50 B; I_C =100 mA; P_D =150 mBT; h_{21} =100600; f_T >250 MFu; R_1 =100 kOm	SOT416,SC75A	100000 600
09	DTC115TKA	ROHM	Dnpn	$V_{\rm CB0}$ = 50 B; $I_{\rm C}$ = 100 MA; $P_{\rm D}$ = 200 MBT; $h_{\rm 21}$ = 100600; $f_{\rm T}$ > 250 MFU; $R_{\rm 1}$ = 100 KOM	SOT346,SC59	225 8
09	DTC115TUA	ROHM	Dnpn	$V_{\rm CB0}$ = 50 B; $I_{\rm C}$ = 100 MA; $P_{\rm D}$ = 200 MBT; $h_{\rm 21}$ = 100600; $f_{\rm T}$ > 250 MFU; $R_{\rm 1}$ = 100 kOM	SOT323,SC70	B-E-C
09	PDTC114EE	PHIL	Dnpn	V _{C80} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ > 30; 10 кОм/10 кОм	SOT416,SC75A	B-E-C
09	PDTC114EEF	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ >30; 10 кОм/10 кОм	SOT490,SC89	B-E-C
DA	DTC125TKA	ROHM	Dnpn	$V_{\rm C80}$ =50 B; $I_{\rm C}$ =100 κA; $P_{\rm D}$ =200 мBτ; $h_{\rm 21}$ =100600; $f_{\rm T}$ >250 ΜΓц; $R_{\rm 1}$ =200 кОм	SOT346,SC59	
DA	DTC125TUA	ROHM	Dnpn	$V_{\rm C80}$ = 50 B; $I_{\rm C}$ = 100 MA; $P_{\rm D}$ = 200 MBT; $h_{\rm 21}$ = 100600; $f_{\rm T}$ > 250 MFu; $R_{\rm 1}$ = 200 kOm	SOT323,SC70	B-E-C
10	MRF9411LT1	MOT	npn	V _{C80} =20 B; I _C =50 mA; P _D =250 mBr; h ₂₁ =50200; f _T =8 fT _U	SOT323,SC70	B-E-C
100	SSTPAD100	SIL	dl	$V_R=55B$; $I_F \le 10 \text{ mA}$; $V_E (I_F=1 \text{ mA}) \le 1.5B$; $I_R \le 100 \text{ mA}$; $C_T \le 2 \text{ m}$	SOT23,SOD23	K•K•A
10A	MMBZ10VAL	ON	dz×2	V ₂ (I _{ZT} =1 mA)=9.510.5B; V _E (I _E =10 mA)<0.9B	SOT23,SOD23	K1-K2-A1,A2
10A	PZM10NB2A	PHIL	dz×2	V _Z (I _{ZT} =5 mA)=9.7710.21 B; Z _{ZT} (I _{ZT} =5 mA)<10 Om	SOT346,SC59	K1-K2-A1,A2
VOI	PZM10NB	PHIL	dz	V _Z (I _{ZT} =5 mA)=9.4510.55B; Z _{ZT} (I _{ZT} =5 mA)<10 0m	SOT346,SC59	A·n.c.·K
IOX	02CZ10	TOSH	dz	V ₂ (I ₂ =5 mA)=9.4010.60B; I ₄ (V _B =8.0B)<0.5 mkA; Z ₂₇ (I ₂₇ =0.5 mA)<120 0m	SOT346,SC59	A•n.c.•K
11	MRF9511LT1	MOT	non	V _{GBB} =20 B; I _G =100 мА; P _B =322 мВт; h ₂₁ =50200; f _T =8 ГГц	SOT323,SC70	B-E-C
11	PDTA114TE	PHIL	Dono	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBr; h ₂₁ >200; R ₁ 10 kOm	SOT416,SC75A	B-E-C
111	DTA113ZUA	ROHM	Dono	V _{CR0} =50 B; I _C =100 MA; P _D =200 MB; h ₂₁ >33; f _T >250 MFu; R ₁ /R ₂ =1/10 kOM	SOT323.SC70	
113	DTA143ZUA	ROHM	Dono	V _{CR0} =50 B; I _C =100 мA; P _D =200 мBт; h ₂₁ >80; f _T >250 МГц;	SOT323,SC70	- T
			-91.49	R ₁ /R ₂ =4.7/47 KOM		



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
11A	PZM11NB2A	PHIL	dz×2	V _Z (I _{ZT} =5 мA)=10.7611.22 B; Z _{ZT} (I _{ZT} =5 мA)<10 Om	SOT346,SC59	K1 · K2 · A1,A2
1V	PZM11NB	PHIL	dz	V _Z (I _{ZT} =5 mA)=10.4411.56 B; Z _{ZT} (I _{ZT} =5 mA)<10 Om	SOT346,SC59	A·n.c.·K
11X	02CZ11	TOSH	dz	V _Z (I _{ZT} =5 mA)=10.4011.60 B; I _L (V _R =8.5B)<0.5 mkA; Z _{Z1} (I _{ZT} =0.5 mA)<120 0 m	SOT346,SC59	A•n.c.•K
2	DTA123EE	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_0 =150 mB τ ; h_{21} >20; f_T >250 MF μ ; R_1/R_2 =2.2/2.2 KOM	SOT416,SC75A	B.E.C
2	DTA123EKA	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_0 =200 mBT; h_{21} >20; f_1 >250 MF μ ; R_1/R_2 =2.2/2.2 KOM	SOT346,SC59	B·E·C
2	DTA123EUA	ROHM	Dpnp	$V_{CB0}^{-}50B; l_{C}^{-}100$ MA; $P_{0}^{-}200$ MBT; $h_{21}^{+}>20; f_{7}^{-}>250$ MF μ ; $R_{1}/R_{2}^{-}2.2/2.2$ KOM	SOT323,SC70	B•E•C
2	PDTC114YEF	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 мA; P _D =200 мВт; h ₂₁ >100; 10 кОм/47 кОм	SOT490,SC89	B·E·C
21	DTC113ZUA	ROHM	Dnpn	V_{CB0} =50 B; I_C = 100 mA; P_D =200 mBT; h_{21} > 33; f_T > 250 MF μ ; R_1/R_2 =1/10 kOm	SOT323,SC70	B-E-C
23	DTC143ZUA	ROHM	Dnpn	V_{CB0} =50 B; I_C =100 mA; P_0 =200 mB τ ; h_{21} >80; f_1 >250 MF μ ; R_1/R_2 =4.7/47 κOm	SOT323,SC70	B-E-C
2A	MMBD1502A	NS		V _R <180 B; I _F <600 mA; V _F (I _F =200 mA)<1.1 B; C _D <4πΦ	SOT23,SOD23	n.cA-K
2A	MMBZ10VAL	ON	dz×2	V ₂ (I _{ZT} =1 mA)=11.412.6B; V _E (I _E =10 mA)<0.9B	SOT23,SOD23	K1 · K2 · A1,A2
2A	PZM12NB2A	PHIL	dz×2	V _Z (I _{ZT} =5 mA)=11.7412.24 B; Z _{ZT} (I _{ZT} =5 mA)<10 Om	SOT346,SC59	K1 · K2 · A1, A2
2E	ZC2812E	ZETEX	shd×2	$V_R \le 15B$; $V_R (I_F = 1 \text{ MA}) \le 0.41B$; $I_R \le 0.1 \text{ MKA}$; $C_D \le 1.2 \text{ m}$	SOT23,SOD23	A1 • K2 • K1 ,A2
2V	PZM12NB	PHIL	dz	V _Z (I _{ZT} =5 mA)=11.4212.60 B; Z _{ZT} (I _{ZT} =5 mA)<10 Om	SOT346,SC59	10.000000000000000000000000000000000000
2X	02CZ12	TOSH	dz	V _Z (I _{ZT} =5 MA)=11.4012.60 B; I _L (V _R =9.0 B)<0.5 MKA; Z _{Z1} (I _{ZT} =0.5 MA)<1100 M	SOT346,SC59	A•n.c.•K
3	BAS125	SIEM	shd	$V_R < 25B$; $I_F < 100 \text{ mA}$; $V_F (I_F = 35 \text{ mA}) < 0.9 B$; $I_R < 1.0 \text{ mrA}$; $C_D < 1.1 \text{ n}\Phi$	SOT23,SOD23	A+n.c.+K
13	DTA143ECA	ROHM	Dpnp	V_{CB0} =50 B; I_c = 100 MA; P_0 =150 MB τ ; h_{21} >20; t_T >250 MF τ ; R_1/R_2 =4.7/4.7 KOM	SOT23,SOD23	B-E-C
3	DTA143EE	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 MA; P_0 =150 MBT; h_{21} >20; f_T >250 MFu; R_1/R_2 =4.7/4.7 KOM	SOT416,SC75A	B.E.C
3	DTA143EKA	ROHM	Dpnip	V_{CB0} -50 B; I_c = 100 mA; P_0 =200 mB τ ; h_{21} >20; $\tilde{\tau}_1$ >250 M Γ u; R_1/R_2 =4.7/4.7 kOm	SOT346,SC59	B·E·C
13	DTA143EUA	ROHM	Dpnp	V_{CB0} =50 B; I_c = 100 MA; P_0 =200 MB τ ; h_{21} >20; $\tilde{\tau}_1$ >250 M Γ u; P_1/P_2 =4.7/4.7 kOM	SOT323,SC70	B·E·C
13	MA4CS103A	M/A	shd	V _R =20B; I _E <100 mA; V _E (I _E =35 mA)<1 B; C _D <1.2 πΦ	SOT23,SOD23	A·n.c.·K
32	DTA123JE	ROHM	Dpnp	V_{CB0} =50 B; I_{c} =100 MA; P_{D} =150 MBT; h_{21} >80; \hat{t}_{1} >250 MF u ; R_{1}/R_{2} =2.2/47 kOM	SOT416,SC75A	B-E-C
132	DTA123JUA	ROHM	Dpnip	V_{CB0} =50 B, I_{c} =100 мA; P_{0} =200 мВт; h_{21} >80; t_{1} >250 МГц; P_{1}/P_{2} =2.2/47 кОм	SOT323,SC70	B•E•C
I3A	PZM13NB2A	PHIL	dz×2	V _Z (I _{ZT} =5 mA)=12.9113.49 B; Z _{ZT} (I _{ZT} =5 mA)<10 Om	SOT346,SC59	K1 · K2 · A1, A2
3E	ZC2813E	ZETEX	shd×2	$V_R \le 15B$; $V_R (I_F = 1 \text{ mA}) \le 0.41B$; $I_R \le 0.1 \text{ m/A}$; $C_D \le 1.2 \text{ m}$	SOT23,SOD23	
3s	BAS125	INF	shd	$V_R \le 25B$; $I_F \le 100$ mA; $V_F (I_F = 35$ mA) ≤ 0.9 B; $I_R \le 0.015$ mkA; $C_D \le 1.1$ m Φ	SOT23,SOD23	A+n.c.+K
3s	BAS125W	SIEM	shd	V_R <25B; I_F <100 mA; V_F (I_F =35 mA)<0.9 B; I_R <0.15 mrA; C_D <1.1 m Φ	SOT323,SC70	A·n.c.·K
3V	PZM13NB	PHIL	dz	V _Z (I _{ZT} =5 mA)=12.4713.96 B; Z _{ZT} (I _{ZT} =5 mA)<10 Om	SOT346,SC59	
3X	02CZ13	TOSH	dz	V _Z (I _{ZT} =5 MA)=12.4014.10 B; I _L (V _R =10B)<0.5 MKA; Z _{Z1} (I _{ZT} =0.5 MA)<110 OM	SOT346,SC59	A•n.c.•K
4	BAS125-04	SIEM	shd×2	$V_R < 25B$; $I_F < 100$ mA; $V_F (I_{F^2} 35$ mA) < 0.9 B; $I_R < 1.0$ mkA; $C_D < 1.1$ n Φ	SOT23,SOD23	
4	BAS125-04W	SIEM	shd×2	$V_R < 25B$; $I_F < 100$ mA; $V_F (I_{F^*} 35$ mA) < 0.9 B; $I_R < 0.15$ mkA; $C_D < 1.1$ m Φ	SOT323,SC70	
4	DTA114EE	ROHM	Dpnp	V_{CB0} =50B; I_C =100mA; P_D =150mBr; h_{21} >30; f_T >250MFu; R_1/R_2 =10/10kOm		12626.1.1.80
4	DTA114EKA	ROHM	Dpnp	V_{CB0} =50 B; I_C = 100 mA; P_D =200 mBt; h_{21} >30; f_T >250 MFu; R_1/R_2 = 10/10 kOm	SOT346,SC59	
4	DTA114EUA	ROHM	Dpnp	V_{CB0} =50 B; I_C =50 mA; P_D =200 mBT; h_{21} >30; f_T >250 MTu; R_1/R_2 =10/10 kOm	SOT323,SC70	
4	MMBD1504	NS	dl×2	$V_R < 180 \text{ B}; I_F < 600 \text{ mA}; V_F (I_F = 200 \text{ mA}) < 1.1 \text{ B}; C_D < 4 \text{ n}\Phi$	SOT23,SOD23	
42	DTC123JUA	ROHM	Dnpn	$\begin{array}{l} V_{CB0}\text{=}50B_{1}I_{c}\text{=}100\text{mA};P_{D}\text{=}200\text{mB}\text{T};h_{21}\text{>}80;f_{7}\text{>}250\text{MFu};\\ R_{1}/R_{2}\text{=}2.2/47\text{kOM} \end{array}$	S0T323,SC70	
4s	BAS125-04	INF	shd×2	$V_R < 25B$; $I_F < 100$ mA; $V_F (I_{F^2} 35$ mA) < 0.9 B; $I_R < 0.015$ m kA; $C_D < 1.1$ n Φ	SOT23,SOD23	
4s	BAS125-04W	INF	shd×2	$V_R < 25B$; $I_F < 100$ mA; $V_F (I_F = 35$ mA) < 0.9 B; $I_R < 0.015$ m kA; $C_D < 1.1$ n Φ	SOT323,SC70	
5	BAS125-05	SIEM	shd×2	$V_B < 25B$; $I_e < 100$ mA; $V_e (I_e = 35$ mA) < 0.9 B; $I_B < 1.0$ mcA; $C_D < 1.1$ n Φ	SOT23,SOD23	
5	BAS125-05W	SIEM	shd×2		SOT323,SC70	
15	DTA124EE	ROHM	Dpnp	V_{CB0} =50 B; $I_{C(max)}$ =100 mA; P_0 =150 mB τ ; h_{21} >56; f_1 >250 M Γ_U ; R_1/R_2 =22/22 kOm	SOT416,SC75A	B-E-C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
15	DTA124EKA	ROHM	Dpnp	V _{C80} =50 B; I _C =30 mA; P _D =200 mBT; h ₂₁ >56; f _T >250 MFu; R ₁ /R ₂ =22/22 kOm	SOT346,SC59	B-E-C
15	DTA124EUA	ROHM	Donp	V _{CB0} =50 B; I _C =30 mA; P _D =200 mBT; h ₂₁ >56; f ₁ >250 MFu; R ₁ /R ₂ =22/22 kOm	SOT323,SC70	B·E·C
15	MMBD1505	NS	dl×2	V _B <180 B; I _E <600 mA; V _E (I _E =200 mA)<1.1 B; C _D <4 πΦ	SOT23,SOD23	K1-K2-A1,A2
15	MMBT3960	MOT	non	V _{CR0} =20B; P _D =300 MBT; h ₂₁ =30300	SOT23,SOD23	B-E-C
156	DTA144VUA	ROHM	Dono	V _{C80} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >33; f _T >250 MFц; R ₁ /R ₂ =47/10 kOm		
15A	MMBZ15VAL	ON	dz×2	V ₂ (I ₂₇ =1 mÅ)=14.2515.75B; V ₄ (I ₆ =10 mÅ)<0.9B	SOT23.SOD23	
15A	PZM15NB2A	PHIL	dz×2	V ₂ (I _{ZT} =5 mA)=14.3414.98B; Z _{ZT} (I _{ZT} =5 mA)<150m	SOT346.SC59	K1-K2-A1-A2
15s	BAS125-05	INF	shd×2	V _R <25B; I _F <100 mA; V _F (I _F =35 mA)<0.9B; I _R <1.0 mKA; C _D <1.1 nΦ	SOT23,SOD23	100 000 000 000
15s	BAS125-05W	INF	shd×2	V _B <25B; I _E <100 mA; V _E (I _E =35 mA)<0.9B; I _B <1.0 mKA; C _B <1.1 mΦ		A1 · A2 · K2 K1
15V	PZM15NB	PHIL	dz	V ₂ (I _{2T} =5 mA)=13.8415.52B; Z _{2T} (I _{2T} =5 mA)<15 Om		A·n.c.·K
15X	02CZ15	TOSH	dz	V ₂ (I _{ZT} =5 mA)=13.8015.60 B; I _L (V _B =11B)<0.5 mcA; Z _{ZT} (I _{ZT} =0.5 mA)<110 Om	-	A·n.c.·K
16	BAS125-06W	SIEM	shd×2	V _B <25B; I _E <100mA; V _E (I _E =35mA)<0.9B; I _B <0.15mkA; C _D <1.1πΦ	SOT323,SC70	K1-K2-A1.A2
16	DTA144EE	ROHM	Dpnp	V_{C80} =50 B; $I_{C(mpq)}$ =100 mA; P_0 =150 mB τ ; h_{21} >68; $\hat{\tau}_1$ >250 MF τ ; R_1 /R $_2$ =47/47 kOm	SOT416,SC75A	
16	DTA144EKA	ROHM	Donp	V _{CB0} =50 B; I _C =30 mA; P _D =200 mBT; h ₂₁ >68; f _T >250 MFu; R ₁ /R ₂ =47/47 kOm	SOT346,SC59	B·E·C
16	DTA144EUA	ROHM	Dpnp	V_{C80} =508; $I_{C(mpq)}$ =100 MA; P_0 =200 MBT; h_{21} >68; f_1 >250 MFu; R_1/R_2 =47/47 kOM	SOT323,SC70	B-E-C
166	DTC144VUA	ROHM	Dnpn	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBT; $h_{21}>33$; $f_T>250 MFu; R_1/R_2=47/10 kOm$	SOT323,SC70	B-E-C
16s	BAS125-06	SIEM	shd×2	V _B <25B; I _E <100 мA; V _E (I _E =35 мA)<0.9 B; I _B <1.0 мкA; C _D <1.1 пФ	SOT23,SOD23	K1-K2-A1,A2
16s	BAS125-06W	INF	shd×2	V _R <25B; I _E <100mA; V _E (I _E =35mA)<0.9B; I _R <1.0mκA; C ₀ <1.1πΦ	SOT323,SC70	K1-K2-A1,A2
16V	PZM 16NB	PHIL	dz	V ₂ (I ₂₇ =5 MÅ)=15.3717.09 B; Z ₂₇ (I ₂₇ =5 MÅ)<20 OM	SOT346,SC59	A·n.c.·K
16X	02CZ16	TOSH	dz	V _Z (I _{ZT} =5 mA)=15.3017.10B; I _L (V _R =12B)<0.5 mrA; Z _{ZT} (I _{ZT} =0.5 mA)<150 0 m	SOT346,SC59	A·n.c.·K
179	DTA115UU	ROHM	Dpnp	V _{CB0} =50 B; I _C =100 мA; P _D =200 мВт; h ₂₁ >27; f _T >250 МГц	SOT323,SC70	B·E·C
179	FMMT5179	ZETEX	npn	V _{CB0} =20B; I _C =50 MA; P _D =330 MBT; h ₂₁ =25250; f _T >1100 MFu	SOT23,SOD23	B-E-C
18	PDTC143ZK	PHIL	Dnpn	V _{CB0} =50B; I _C =100 MA; P _D =250 MBT; h ₂₁ >100; 4.7 KOM/47 KOM	SOT346,SC59	B·E·C
181	BFQ181	SIEM	npn	V _{C80} =20B; I _C =20 мA; P _D =200 мВт	SOT23,SOD23	B·E·C
182	BFO182	SIEM	npn	V _{CB0} =20B; I _C =35 MA; P _D =250 MBT; h ₂₁ >50; f _T >8 ITU	SOT23,SOD23	B-E-C
183	DTC115UU	ROHM	Dnon	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ > 27; f _T >250 MFu,	SOT323.SC70	
18A	CMPZ5221B	CSI	dz	V ₂ (I _{2T} =20 mA)= 2.282.52B; I ₁ (V _R =1.0B) < 100 mKA; Z _{2T} (I _{2T} =20 mA) < 30 Om	SOT23,SOD23	A·n.c.·K
18A	MMBZ18VAL	ON	dz×2	V ₂ (I _{2T} =1 mA)=17.118.9 B; V _E (I _E =10 mA)<0.9 B	SOT23.SOD23	100000000000000000000000000000000000000
18A	MMBZ5221BLT1	ON	dz	V ₂ (I _{2T} =20 mA)= 2.282.52B; I _B < 100 mkA	SOT23,SOD23	
18B	CMPZ5222B	CSI	dz	V _Z (I _{ZT} =20 mA)=2.3752.625 B; I _z (V _R =1.0 B)<100 mkA; Z _{ZT} (I _{ZT} =20 mA)<30 0 m	SOT23,SOD23	110000000000000000000000000000000000000
18B	MMBZ5222BLT1	ON	dz	V ₂ (I _{2T} =20 mA)= 2.372.63B; I _B < 100 mkA	SOT23,SOD23	A·n.c.·K
18C	CMPZ5223B	CSI	dz	V ₂ (I _{2T} =20 mA)=2.5652.835 B; I ₁ (V _B =1.0 B)<75 mkA; Z _{2T} (I _{2T} =20 mA)<30 Om		
18C	MMBZ5223BLT1	ON	dz	V ₂ (I _{2T} =20 mA)=2.572.84B; I _B <75 mrA	SOT23,SOD23	
18D	CMPZ5224B	CSI	dz	$V_2(I_{ZT}=20 \text{ mA})=2.662.94 \text{ B}; I_1(V_B=1.0 \text{ B})<75 \text{ mrA}; Z_{ZT}(I_{ZT}=20 \text{ mA})<30 \text{ Om}$	SOT23.SOD23	ESCHARACIONES
18D	MMBZ5224BLT1	ON	dz	V ₂ (I _{2T} =20 mA)=2.662.94B; I _R <75 mrA	SOT23,SOD23	200700001.0000
18E	CMPZ5225B	CSI	dz	$V_2(I_{71}=20 \text{ mA})=2.853.15 \text{ B; }I_1(V_{B}=1.0 \text{ B})<50 \text{ m; A; }Z_{77}(I_{71}=20 \text{ mA})<29 \text{ Om}$	SOT23,SOD23	
18E	MMBZ5225B	VISH	dz	V ₂ (I _{2T} =20 mA)=2.853.15B; I _R <50 mkA	SOT23.SOD23	
18E	MMBZ5225BLT1	ON	dz	V ₂ (I ₂₁ =20 mA)= 2.853.15B; I _R < 50 m kA	SOT23,SOD23	
18F	MMBZ5260B	VISH	dz	V ₂ (I ₂₁ =3 MA)=40.8545.15B; I _B <0.1 MKA	SOT23,SOD23	
18V	PZM18NB	PHIL	dz	V _Z (I _{ZT} =5 MA)=16.9419.03B; Z _{ZT} (I _{ZT} =5 MA)<20 Om	SOT346.SC59	
18X	02CZ18	TOSH	dz	$V_Z(I_{ZT}=5 \text{ MA})=16.8019.10B; I_L(V_R=14B)<0.5 \text{mKA}; \\ Z_{ZT}(I_{ZT}=0.5 \text{ MA})<150 \text{ OM}$	SOT346,SC59	100110000000000000000000000000000000000
19	DTA115EE	ROHM	Dpnp	V_{C80}^{-} :50B; $I_{C(100)}^{-}$:100; P_{D}^{-} :150 MBT; h_{21} >82; f_{T} >250 MF $_{L}$; P_{L} / P_{0} :100 KQM	SOT416,SC75A	B-E-C
19	DTA115EKA	ROHM	Dono	V _{C80} =50 B; I _C =30; P _D =200 мBτ; h ₂₁ >82; f _T >250 MΓιι; R ₁ /R ₂ =100/100 κOm	SOT346.SC59	B-F-C
19	DTA115EUA	ROHM	Dpnp	V_{C80} -50 B; I_C -20 MB; P_0 -200 MB; h_{21} >82; f_T >250 MFu; P_1/P_0 -100/100 KOM	SOT323,SC70	10000
19	PDTA143ZK	PHIL	Dono	V _{CB0} =50 B; I _C =100 MA; P _D =250 MBT; h ₂₁ >100; 4.7 KOM/47 KOM	SOT346,SC59	B-F-C
IA	BC846A	CDIL	nan	V ₀₈₀ =80 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =110220; f _T >100 MF _U	SOT23,SOD23	

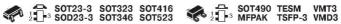




Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
1A	BC846A	TOSH	npn	V _{CB0} = 80 B; I _C = 100 мA; P _D = 150 мВт; h ₂₁ = 110220; f _T = 300 МГц	SOT23,SOD23	B·E·C
1A	BC846A	DIODS	npn	V _{CB0} =80 B; I _C = 100 мА; P _D =150 мВт; h ₂₁ =110220; f _T =300 МГц	SOT23,SOD23	B·E·C
1A	BC846A	VISH	npn	V _{CB0} =80 B; I _C =100 мА; P _D =310 мВт; h ₂₁ =110220; f _T >300 МГц	SOT23,SOD23	B·E·C
1A	BC846AF	PHIL	npn	V _{CB0} =80 B; I _C =100 мА; P _D =250 мВт; h ₂₁ =110220; f _T >100 МГц	SOT490,SC89	B·E·C
1A	BC846ALT1	MOT	npn	V _{CBD} =80 B; I _C =100 мA; P _D =300 мВт; h ₂₁ =110220; f _T >100 МГц	SOT23,SOD23	B·E·C
1A	BC846AT	PHIL	npn	V _{CBD} =80 B; I _C =100 мA; P _D =150 мВт; h ₂₁ =110220; f _T >100 МГц	S0T416,SC75A	B·E·C
1A	BC846AWT1	MOT	non	V _{сво} =80 B; I _c =100 мA; P _c =300 мВт; h _{ct} =110220; f _T >100 МГц	S0T323,SC70	B·E·C
1A	BC846AWT1	LRC	non	V _{сво} =80 B; I _с =100 мА; Р _о =300 мВт; h ₂₁ =110220; f _T >100 МГц	S0T323,SC70	B·E·C
1A	BC846AWT1	ON	non	V _{CR0} =80 B; I _C =100 мA; P _D =300 мВт; h _{P1} =110220; f _T >100 МГц	S0T323,SC70	B·E·C
1A	FMMT3904	мот	non	V _{CB0} =60 B; I _C =200 мА; P _D =330 мВт; h _{Pl} =100300; f _T >300 МГц	SOT23.SOD23	
1A	FMMT3904	ZETEX	non	V _{сво} =60 B; I _c =200 мА; P _D =330 мВт; h _H =100300; f _T >300 МГц	SOT23,SOD23	B·E·C
1A	IRLML2402	IR	nMOS	HEXFET; V _{DS} =20 B; I _D =0.9A; P _D =540 MBT; R _{DS(en)} < 0.35 OM	SOT23.SOD23	1001275100
1A	KST3904	SAMS	non	V _{CBD} =60B; I _C =100мA; P _D =200мBт; h _{D1} =100300; f _T >300МГц	SOT23,SOD23	Address of the second
1A	MMBT3904	VISH	non	V _{CB0} =60 B; I _C =100 MA; P _D =200 MB; h ₂₁ =100300; f _T >300 MF _U	SOT23.SOD23	
1A	TMPT3904	ALLEG	non	V _{CR0} =60 B; I _C =100 MA; P _D =200 MBT; h ₂₁ =100300; f _T >300 MFu	SOT23,SOD23	0.00.00
-1A	PMST3904	PHIL	non	V _{CR0} =60 B; I _C =200 MA; P _D =200 MBT; h ₂₁ =100300; f _T >300	S0T323,SC70	
1A-	BC846AW	PHIL	non	V _{CBD} =80 B; I _C =100 mA; P _D =200 mBr; I _{D2} =110220; f _T >100 MFu	S0T323,SC70	
1AG	2SC3339GR	TOSH	non	V _{CD} =50 B; I _C =150 MA; P _D =250 MBT; h ₂₁ =710220; τ ₇ >100 MTu	SOT23,SOD23	
1AL	2SC3339BL	TOSH	non	V _{cm} =50 B; I _c =150 мA; P _n =150 мВт; h ₂₁ =350700; f _T >80 МГц	SOT23,SOD23	and the second second
1AM	MMBT3904LT1	MOT	non	V _{CR0} =60 B; I _C =200 MA; P _D =300 MBT; h ₂₁ =100300; f _T >200 MFц	SOT23,SOD23	
1AO	2SC33390	TOSH	non	V _{CB1} =50 B; I _C =150 мA; P _D =300 мВт; h ₂₁ =70140; f _T >80 МГц	SOT23,SOD23	182.80 (2)
1Ao	BC846A	PHIL	'	V _{CBD} =30 B, I _C =130 мА, P _D =130 мВ1, I ₁₂₁ =70 140, I _T >80 МIЦ V _{CBD} =80 B; I _C =100 мА; P _D =250 мВт; I _{D1} =110220; I _T >100 МГц	SOT23,SOD23	
IAQ	2SB779Q	PAN	npn		SOT23,SOD23	
IAQ IAR	TO SOUTH THE SECOND SEC	PAN	pnp	V _{CB0} =25B; I _C =500mA; P _D =200mBr; h ₂₁ =90155; f _T =150MFu		100000000000000000000000000000000000000
	2SB779R		pnp	V _{CB0} =25B; I _C =500мA; P _D =200мBт; h ₂₁ =130220; f _T =150МГц	SOT23,SOD23	
1AR	BC846AR	PHIL	npn	V _{CB0} =65B; I _C =100mA; P _D =310mBr; h ₂₁ =220; f _T >300MFu	SOT23,SOD23	
1As	BC846A	INF	npn	V _{CB0} =80 B; I _C =100 mA; P _D =330 mBr; h ₂₁ =110220; f _T =250 MFu	S0T23,S0D23	100000
1As	BC846AT	INF	npn	V _{CB0} =80 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =110220; f _T =250 MFu	S0T416,SC75A	
1As	BC846AW	INF	npn	V _{C80} =80 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =110220; f _T =250 МГц	S0T323,SC70	
1At	BC846A	PHIL	npn	V _{CB0} =80 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =110220; f _T >100 МГц	SOT23,SOD23	
1At	BC846AW	PHIL	npn	V _{CBO} =80 B; I _C = 100 мА; P _D =200 мВт; h ₂₁ =110220; f _T >100 МГц	S0T323,SC70	10/20/07/20/000
1AY	2SC3339Y	TOSH	npn	V _{CBO} =50 B; I _C =150 мA; P _O =150 мВт; h ₂₁ =120240; f ₁ >80 МГц	SOT23,SOD23	200000000000000000000000000000000000000
1B	BC846B	CDIL	npn	V _{CB0} =80 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ =200450; f _T > 100 МГц	SOT23,SOD23	
1B	BC846B	TOSH	npn	V _{CB0} =80 B; I _C =100 мA; P _D =150 мВт; h ₂₁ =200450; f _T =300 МГц	SOT23,SOD23	
1B	BC846B	DIODS	npn	V _{CB0} =80 B; I _C =100 mA; P _D =300 mBt; h ₂₁ =200450; f _T =300 MFu,	SOT23,SOD23	B·E·C
1B	BC846B	VISH	npn	V_{CB0} =80 B; I_C =100 mA; P_D =310 mBt; h_{21} =200450; f_T >300 MFu	SOT23,SOD23	B·E·C
1B	BC846B	ZETEX	npn	V_{CB0} =80 B; I_C =100 mA; P_D =330 mBr; h_{21} =200450; f_T >300 M Γ_L	SOT23,SOD23	B·E·C
1B	BC846BF	PHIL	npn	V_{CB0} =80 B; I_C =100 mA; P_D =250 mBT; h_{21} =200450; f_T >100 M Γ_{II}	SOT490,SC89	B·E·C
1B	BC846BLT1	MOT	npn	V _{CB0} =80 B; I _C =100 мA; P _D =300 мВт; h ₂₁ =200450; f _T >100 МГц	SOT23,SOD23	B·E·C
1B	BC846BT	PHIL	npn	V_{CB0} =80 B; I_C =100 mA; P_D =330 mBr; h_{21} =200450; f_T >100 M Γ_{LL}	S0T416,SC75A	B·E·C
1B	BC846BWT1	LRC	npn	V_{CB0} =80 B; I_C =100 mA; P_D =200 mBT; h_{21} =200450; f_T >100 M Γ_U	S0T323,SC70	B·E·C
1B	BC846BWT1	ON	npn	V _{CB0} =80 B; I _C =100 мA; P _D =200 мВт; h ₂₁ =200450; f _T >100 МГц	S0T323,SC70	B-E-C
1B	IRLML2803	IR	nMOS	HEXFET; V _{DS} =30 B; I _D =0.9 A; P _D =540 MBT; R _{DS(on)} < 0.4 OM	SOT23,SOD23	G·S·D
1B	KST2222	SAMS	npn	V _{CB0} =60 B; I _C =600 мА; P _D =350 мВт; h ₂₁ > 75; f _T >250 МГц	SOT23,SOD23	B·E·C
1B	TMPT2222	ALLEG	npn	V _{CB0} =60 B; I _{CB0} <10 нA; h ₂₁ =100300; V _{CE(sat)} <0.4 B; f _T >250 МГц	S0T23,S0D23	B·E·C
-1B	PMST2222	PHIL	npn	V _{CB0} =60B; I _C =600 мA; P _D =200 мВт; h ₂₁ =100300; f _T >250 МГц	S0T323,SC70	B·E·C
1B-	BC846BW	PHIL	npn	V _{CB0} =80 B; I _C = 100 мА; P _D =200 мВт; h ₂₁ =200450; f _T > 100 МГц	S0T323,SC70	B·E·C
1BG	2SC3340GR	TOSH	npn	V _{CF0} =120 B; k ₀ =100 мA; P ₀ =150 мВт; h ₂₁ =200400; f ₇ >100 МГц	SOT23,SOD23	B·E·C
1BL	2SC3340BL	TOSH	non	V _{CED} =120 B; I _C =100 мA; P _D =150 мВт; h ₂₁ =350700; f _T >100 МГц	SOT23,SOD23	
1Bp	BC846B	PHIL	non	V _{CB0} =80 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =200450; f _T >100 MFц	SOT23,SOD23	
1BR	BC846BR	PHIL	non	V _{CB0} =65B; I _C =100 MA; P _D =310 MBr; h ₂₁ =330; f _T >300 MFu	SOT23,SOD23	
1Bs	BC846B	SIEM	non	V _{CR0} =80 B; I _C =100 mA; P _D =330 mBr; h ₂₁ =200450; f _T =250 MFu	SOT23,SOD23	100000000000000000000000000000000000000
1Bs	BC846BT	INF	non	V _{CR0} =80 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =200450; f _T =250 MFu	S0T416,SC75A	

SOT490 TESM VMT3 1 3 SOT523 SOT323 SOT23-3 1 3 SOT523 SOT323 SOT3

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
Bs	BC846BW	INF	npn	V _{CB0} =80 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =200450; f _T =250 MFu	SOT323,SC70	B-E-C
Bt	BC846B	PHIL	npn	V _{гао} =80 B; I _c =100 мA; P ₀ =250 мВт; h ₂₁ =200450; f _T >100 МГц	SOT23,SOD23	B·E·C
Bt	BC846BW	PHIL	npn	V_{O80} =80 B; I_C =100 mA; P_D =200 mBr; h_{21} =200450; f_T >100 MFu	SOT323,SC70	B-E-C
IBZ	FMMT2222	ZETEX	non	V _{CR0} =60 B; I _C =600 mA; P _D =330 mBT; h ₂₁ =100300; f _T >250 MFu	SOT23,SOD23	B-E-C
IC	FMMTA20	ZETEX	npn	V _{GR0} =40 B; I _G =100 mA; P _D =330 mBT; h ₂₁ =40400; f _T >125 MFц	SOT23,SOD23	B·E·C
IC	IRLML6302	IR	oMOS	HEXFET; V _{DS} =20 B; I _D =0.62 A; P _D =540 MBT; P _{DS(m)} < 0.9 OM	SOT23.SOD23	100000000000000000000000000000000000000
IC	KST20	SAMS	npn	V _{GR0} =40 B; I _G =100 мA; P _D =350 мBr; h ₂₁ =40400; f _T >125 МГц	SOT23,SOD23	B·E·C
10	MMBTA20LT1	MOT	ngn	V _{GE0} =40 B; I _G =100 mA; P _D =225 mBτ; h ₂₁ =40400; f _T >125 MΓц	SOT23,SOD23	
1CL	2SC4082L	ROHM	non	V _{CB0} =30 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =2756; f _T =1500 МГц	SOT323.SC70	
1CM	2SC4082M	ROHM	ngn	V _{C80} =30 B; I _C =50 мA; P _D =150 мВт, h ₂₁ =3982; f _T =1500 МГц	SOT323.SC70	
1CN	2SC4082N	ROHM	npn	V _{CB0} =30 B; I _C =50 mA; P _D =150 mBT; h ₂₁ =56120; f _T =1500 MFu	SOT323,SC70	
100	2SC33410	TOSH	non	V _{CEO} =30 B; I _C =500 мА; Р _О =200 мВт; h ₂₁ =70140.; f _T >200 МГц	SOT23.SOD23	1750320000
1CP	2SC4082P	ROHM	npn	V _{C80} =30 B; I _C =50 мА; P _D =150 мВт, h ₂₁ =82180; f _T =1500МГц	SOT323.SC70	
1Co	BAP50-05	PHIL	pin×2	V _R >50 B; I _F <50 mA; V _F (I _F =50 mA)<1.1 B; I _R <0.1 mxA	SOT23.SOD23	Nacco 7 (10)
1CQ	2SC4082Q	ROHM	npn	V _{CB0} =30 B; I _C =50 mA; P _D =150 mBT; h ₂₁ =120270; f _T =1500 MFu	SOT323,SC70	
1CY	2SC3341Y	TOSH	npn	V _{CE0} =30B; I _C =500 мА; Р _D =130 мВТ; 1 ₂₁ =120240.; f _T >200 МГц	SOT23,SOD23	
1D	BC846	CDIL	npn	V _{CB0} =80 B; I _C =100 мA; P _D =250 мBт; I _{P2} =110450; f _T >100 МГц	SOT23,SOD23	
1D	IRLML5103	IR	oMOS		SOT23,30D23	
1D	KST42	SAMS	non	HEXFET; V _{DS} =30 B; I _D =0.61 A; P _D =540 MBT; R _{DS(on)} <10 M		CONT. D.
ID	MBTA42	TOSH	7.00	V _{C80} =300 B; I _C =500 мА; Р _D =350 мВт; h ₂₁ >40; f _T >50 МГц	SOT23,SOD23 SOT23,SOD23	1152 12 130
	100000000000000000000000000000000000000		npn	V _{CBO} =300 B; I _C =500 мА, Р _D =250 мВт; h ₂₁ >40; f _T =50 МГц		3220 22
1D	MMBTA42	VISH	npn	V _{CB0} =300 B; I _C =200 мА, Р _D =350 мВт; h ₂₁ >25; f _T >50 МГц	SOT23,SOD23	
1D	MMBTA42LT1	ON	npn	V _{CBO} =300 B; I _C =500 мА; P _D =225 мВт; h ₂₁ >25; f _T >50 МГц	SOT23,SOD23	
ID.	SMBTA20	VISH	npn	V_{CB0} =40 B; I_C =100 mA; P_D =330 mBr; h_{21} =40400; f_T >125 MF μ	SOT23,SOD23	
1D	TMPTA42	ALLEG	npn	V_{CB0} =300 B; I_{CB0} <100 HA; h_{21} >40; $V_{CE(sat)}$ <0.5 B; f_T >50 M Γ_{LL}	SOT23,SOD23	
1D-	BC846W	PHIL	npn	V _{GB0} =80 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =110450; f _T >100 МГц	SOT323,SC70	100000000000000000000000000000000000000
1D-	BC846W	PHIL	npn	V_{CB0} =80 B; I_C =100 mA; P_D =200 mBr; h_{21} =110450; f_T >100 MFu	SOT323,SC70	T00= 0
1DL	2SC4083L	ROHM	npn	V _{C80} =20 B; I _C =50 мА; Р _D =150 мВт; h ₂₁ =2756; f _T =3200 МГц	SOT323,SC70	
1DM	2SC4083M	ROHM	npn	V _{C80} =20 B; I _C =50 мА; Р _D =150 мВт; h ₂₁ =3982; f _T =3200 МГц	SOT323,SC70	
1DN	2SC4083N	ROHM	npn	V _{CBO} =20 B; I _C =50 мА; Р _D =150 мВт; h ₂₁ =56120; f _T =3200 МГц	SOT323,SC70	
1DP	2SC4083P	ROHM	npn	V _{CB0} =20 B; I _C =50 мА; Р ₀ =150 мВт; h ₂₁ =82180; f ₁ =3200 МГц	SOT323,SC70	
1Dp	BC846	PHIL	npn	V_{C80} =80 B; I_C =100 mA; P_D =250 mBt; h_{21} =110450; f_T >100 M Γ_U	SOT23,SOD23	1000000
1DQ	2SC4083Q	ROHM	npn	V _{G80} =20 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =120270; f _T =3200 МГц	SOT323,SC70	
1DR	2SD1328R	PAN	npn	V _{GB0} =25 B; I _C =500 мА; P _D =200 мВт; h ₂₁ =200350	SOT346,SC59	
1DR	MSD1328R	MOT	npn	V _{CB0} =25B; I _C =500 мA	SOT346,SC59	
1DS	2SD1328S	PAN	npn	V _{C80} =25 B; I _C =500 мА; P _D =200 мВт; h ₂₁ =300500	SOT346,SC59	B·E·C
1DT	2SD1328T	PAN	npn	V _{C80} =25B; I _C =500 мА; P ₀ =200 мВт; h ₂₁ =400800	SOT346,SC59	B·E·C
1Dt	BC846	PHIL	npn	V_{C80} =80 B; I_C =100 mA; P_D =250 mBr; h_{21} =110450; f_T >100 M Γ_{IJ}	SOT23,SOD23	B-E-C
1Dt	BC846W	PHIL	npn	V_{C80} =80 B; I_C =100 mA; P_D =250 mBt; h_{21} =110450; f_T >100 M Γ_{LL}	S0T323,SC70	B·E·C
1Dt	BC846W	PHIL	npn	V_{C80} =80 B; I_C =100 mA; P_0 =200 mBr; h_{21} =110450; f_T >100 M Γ_U	SOT323,SC70	B·E·C
1E	BC847A	CDIL	npn	V_{CB0} =50 B; I_C =100 mA; P_D =150 mBT; h_{21} =110220; f_T >300 MF $_{LL}$	SOT23,SOD23	B-E-C
1E	BC847A	DIODS	npn	V _{CB0} =50 B; I _C =100 мA; P _D =300 мВт; h ₂₁ =110220; f _T =300 МГц	SOT23,SOD23	B-E-C
1E	BC847A	TOSH	npn	V _{CB0} =50 B; I _C =100 мA; P _D =150 мВт; h ₂₁ =110220; f _T =300 МГц	SOT23,SOD23	B·E·C
1E	BC847A	VISH	npn	V _{G80} =50 B; I _C =100 мA; P _D =310 мВт; h ₂₁ =110220; f _T >300 МГц	SOT23,SOD23	B·E·C
1E	BC847AF	PHIL	npn	V _{G80} =50 B; I _C =100 мА; P _D =250 мВт; h ₂₁ =110220; f _T >100 МГц	SOT490,SC89	B-E-C
1E	BC847ALT1	MOT	npn	V_{CB0} =50 B; I_C =100 mA; P_0 =300 mBr; h_{21} =110220; f_T >100 M Γ_{IJ}	SOT23,SOD23	B-E-C
1E	BC847AT	PHIL	npn	V_{C80} =50 B; I_C =100 mA; P_D =200 mBr; h_{21} =110220; f_T >100 M Γ_{IJ}	SOT416,SC75A	B-E-C
1E	BC847AT	DIODS	npn	V _{CB0} =50 B; I _C =100 mA; P _D =150 mBr; h ₂₁ =110220; f _T >100 MFu	SOT523	B·E·C
1E	BC847AWT1	LRC	npn	V _{G80} =50 B; I _G =100 κA; P _D =250 κBτ; h ₂₁ =110220; f _T >=250 ΜΓμ	SOT323,SC70	
1E	BC847AWT1	ON	npn	V _{GRO} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =110220; f _T >=250 МГц	SOT323,SC70	
1E	FMMTA43	ZETEX	npn	V _{CB0} =200 B; I _C =200 мА; P _D =330 мВт; h ₂₁ =50200; f _T >50 МГц	SOT23,SOD23	A
1E	IRLML6402	IR	pMOS	HEXFET; V _{DS} =20 B; I _D =2.2A; P _D =1.3 BT; R _{DS(on)} <0.135 Om	SOT23,SOD23	-0.000000
	KST43	SAMS	Pillon	V _{CR0} =200 B; I _C =500 MA; P _D =350 MBτ; h ₂₁ >40; f ₇ >50 MΓц	SOT23,SOD23	100000000000000000000000000000000000000





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
E	TMPTA43	ALLEG	npn	V_{CB0} =200B; I_{CB0} <100 HA; h_{21} >40; $V_{CE(sat)}$ <0.5B; f_T >50 MFu,	SOT23,SOD23	B-E-C
E-	BC847AW	PHIL	npn	V _{CRD} =50B; I _C =100 мА; P _D =200 мВт; h ₂₁ =110220; f _T >100 МГц	SOT323,SC70	B·E·C
EL	2SC4084L	ROHM	non	V _{сво} =30 B; I _с =50 мА; P _о =150 мВт; h ₂₁ =2756; f _T >200 МГц	SOT323,SC70	B·E·C
IEM	2SC4084M	ROHM	non	V _{сяп} =30 B; I _с =50 мА; P _п =150 мВт; h ₂₁ =3982; f _T >200 МГц	SOT323.SC70	B·E·C
IEN	2SC4084N	ROHM	non	V _{CRD} =30 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =56120; f _T >200 МГц	SOT323,SC70	B·E·C
IEP	2SC4084P	ROHM	non	V _{GB0} =30 B; I _G =50 мА; P _D =150 мВт; h ₂₁ =82180; f _T >200 МГц	SOT323,SC70	B·E·C
1Eo	BC847A	PHIL	non	V _{CR0} =50 B; I _C = 100 мA; P _D =250 мВт; h ₂₁ =110220; f _T > 100 МГц	SOT23,SOD23	B·E·C
1EQ	2SC4084Q	ROHM	non	V _{CR0} =30B; I _C =50 mA; P _D =150 mBT; h ₂₁ =120270; f _T >200 MFц	SOT323,SC70	
ER	BC847AR	PHIL	non	V _{CR0} =45 B; I _C =100 MA; P _D =310 MBT; h ₂₁ =220; f _T >300 MFu	SOT23.SOD23	
1Es	BC847A	INF	non	V _{CB0} =50B; I _C =100mA; P _D =330mBr; h ₂₁ =110220; f _T =250MFu	SOT23,SOD23	
1Es	BC847A	INF	non	V _{CR0} =50B; I _C =100MA; P _D =330MB; h ₂₁ =110220; f _T =250MFu	SOT23,SOD23	
1Es	BC847AT	INF	non	V _{CB0} =50B; I _C =100mA; P _D =250mB; h ₂₁ =110220; f _T =250MFц	SOT416.SC75A	
IEs	BC847AW	INF	non	V _{CR0} =50 B; I _C =100 мА; P _D =250 мВт; h ₂₁ =110220; f _T >=250 МГц	SOT323.SC70	22000000000
IEt	100000000000000000000000000000000000000	PHIL		000	SOT23.SOD23	200000000000000000000000000000000000000
1Et	BC847A	PHIL	npn	V _{CBO} =50B; I _C =100мA; P _D =250мBr; h ₂₁ =110220; f _T >100МГц		
	BC847AW	-	npn	V _{CB0} =50 B; I _C =100 MA; P _D =200 MBT; h ₂₁ =110220; f _T >100 MFц	SOT323,SC70	
F	BC847B	CDIL	npn	V _{CBO} =50 B; I _C =100 MA; P _D =150 MBT; h ₂₁ =200450; f _T >300 MFц	SOT23,SOD23	
F	BC847B	DIODS	npn	V _{CB0} =50 B; I _C =100 MA; P _D =300 MBr; h ₂₁ =200450; f _T =300 MFц	SOT23,SOD23	
F	BC847B	TOSH	non	V _{CB0} =50 B; I _C =100 мA; P _D =150 мВт; h ₂₁ =200450; f _T =300 МГц	SOT23,SOD23	
F	BC847B	VISH	npn	V _{CBO} =50B; I _C =100 мA; P _D =310 мВт; h ₂₁ =200450; f _T >300 МГц	SOT23,SOD23	
F	BC847B	ZETEX	npn	V _{CB0} =50 B; I _C = 100 мА; P _D =330 мВт; h ₂₁ =200450; f _T >300 МГц	SOT23,SOD23	
1F	BC847BF	PHIL	npn	V _{CB0} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =200450; f _T > 100 МГц	SOT490,SC89	
IF	BC847BLT1	MOT	npn	V_{CB0} =50 B; I_0 =100 mA; P_0 =300 mBT; h_{21} =200450; f_T >100 M Γ_{II}	SOT23,SOD23	B·E·C
IF	BC847BT	PHIL	npn	V_{CB0} =50 B; I_C =100 mA; P_D =150 mBT; h_{21} =200450; f_T >100 M Γ_{II}	SOT416,SC75A	B-E-C
IF	BC847BT	DIODS	non	V_{CB0} =50 B; I_C =100 mA; P_D =150 mBT; h_{21} =200450; f_T >100 M Γ_L	SOT523	B·E·C
IF	BC847BWT1	LRC	npn	V _{CB0} =50 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =200450; f _T >100 МГц	SOT323,SC70	B·E·C
1F	BC847BWT1	ON	non	V _{CB0} =50 B; I _C =100 мA; P _D =200 мВт; h ₂₁ =200450; f _T >100 МГц	SOT323,SC70	B·E·C
1F	BC847CT	DIODS	npn	V _{CB0} =50 B; I _C =100 мA; P _D =150 мВт; h ₂₁ =420800; f _T >100 МГц	SOT523	B·E·C
IF	IRLML6401	IR	pMOS	HEXFET; V _{DS} =12 B; I _D =3.4A; P _D =1.3 BT; R _{DS(ort)} < 0.125 O _M	SOT23,SOD23	G·S·D
1F	KST5550	SAMS	non	V _{сяп} =160 B; I _с =600 мА; P _п =350 мВт; h ₂₁ =60250; f _T >150 МГц	SOT23,SOD23	B·E·C
1F	MMBT5550	MOT	non	V _{GB0} =160 B; I _C =600 MA; P _D =300 MBT; h ₂₁ =60250	SOT23,SOD23	B·E·C
IF-	BC847BW	PHIL	non	V _{CBD} =50 B; I _C = 100 мA; P _D =200 мВт; h ₂₁ =200450; f _T > 100 МГц	SOT323,SC70	B-E-C
1FF	CMPT5551	CSI	non	V _{CBD} =180B; I _C =600 мA; P _D =350 мВт; h ₂₁ =80250; f _T =100300 МГц	SOT23.SOD23	B·E·C
1FP	2SK321P	PAN	nFET	V _{6S} =15B; I _D =5MA; P _D =200 MBT; Q _E >15MCM; I _{DSS} =516 MA	SOT23,SOD23	
1Fo	BC847B	PHIL	non	V _{CR0} =50 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ =200450; f _T > 100 МГц	SOT23.SOD23	
IFQ	2SK321Q	PAN	nFET	V _{GS} = 15B; I _D =5MA; P _D =200 MBT; Q _E > 15 MCM; I _{DSS} = 1424 MA	SOT23,SOD23	
FR	2SK321R	PAN	nFET	V _{GS} *15B; I _D *5MA; P _D *200 MBT; Q _F >15 MCM; I _{DSS} *2032 MA	SOT23.SOD23	
IFR	BC847BR	PHIL	non	V _{cnn} =45B; I _C =100 mA; P _D =200 mBr; I _{D2} =330; f _T >300 MΓμ	SOT23,SOD23	
IFS	2SK321S	PAN	nFET	V _{GS} ⁻ 15B; I _D ⁻ 5MA; P _D ⁻ 200 MB;; g _F >15MCM; I _{DSS} ⁻ 2842 MA	SOT23,30D23	
Fs	BC847B	INF	non	V _{GB} =10B, I _D =3MA, P _D =200 MB1, g _F >10 MCM, I _{DSS} =2642 MA V _{GB} =50B; I _C =100 мA; P _D =330 мB1; h ₂₁ =200450; f _T =250 МГц	SOT23,SOD23	2000
IFS	BC847BT	INF	4.0			
			npn	V _{CBO} =50 B; I _C =100mA; P _D =250mBr; h ₂₁ =200450; f _T =250MFu	SOT416,SC75A	
Fs	BC847BW	INF	npn	V _{CBO} =50 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =200450; f _T =250 MFц	SOT323,SC70	
lFt .	BC847B	PHIL	npn	V _{CB0} =50 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =200450; f _T >100 MFц	SOT23,SOD23	
Ft	BC847BW	PHIL	npn	V _{CB0} =50 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =200450; f _T >100 МГц	S0T323,SC70	
IFZ	FMBT5550	ZETEX	npn	V _{CBO} =140 B	SOT23,SOD23	100000000000000000000000000000000000000
iG	BC847C	CDIL	npn	V _{CB0} =50 B; I _C =100 мА; P _D =310 мВт; h ₂₁ =420800; f _T > 300 МГц	SOT23,SOD23	
IG	BC847C	VISH	npn	V _{CB0} =50B; I _C =100 мA; P _D =310 мВт; h ₂₁ =420800; f _T >300 МГц	SOT23,SOD23	
G	BC847C	ZETEX	npn	V _{CB0} =50 B; I _C =100 мA; P _D =330 мВт; h ₂₁ =420800; f _T >300 МГц	SOT23,SOD23	
IG	BC847C	DIODS	npn	V_{CB0} =50B; I_C =100mA; P_D =300mBT; h_{21} =420800; f_T =300MFu,	SOT23,SOD23	
G	BC847CF	PHIL	npn	V_{CB0} =50B; I_C =100 mA; P_D =250 mBT; h_{21} =420800; f_T >100 M Γ_{II}	SOT490,SC89	B·E·C
IG	BC847CLT1	MOT	npn	V_{CB0} =50 B; I_C =100 mA; P_D =300 mBr; h_{21} =420800; f_T >100 M Γ_{II}	SOT23,SOD23	B·E·C
1G	BC847CT	PHIL	npn	V_{CB0} =50 B; I_C =100 mA; P_D =250 mBr; h_{21} =420800; f_T >100 MFu.	SOT416,SC75A	B.E.C
G	BC847CWT1	LRC	non	V _{CR0} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ =420800; f _T >100 MFu	SOT323,SC70	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
IG	BC847CWT1	ON	npn	V _{CB0} =50 B; I _C =100 MA; P _D =200 MBT; h ₂₁ =420800; f _T >100 MFL	SOT323,SC70	B-E-C
G	FMMTA06	ZETEX	npn	V _{гва} *80 B; I _с *500 мА; Р _о *330 мВт; h ₂₁ >50; f _т >100 МГц	SOT23,SOD23	B·E·C
IG	IRLML2502	IR		HEXFET; V _{DS} =30 B; I _D =3.4A; P _D =1.25 Br; R _{DStont} <0.08 Om	SOT23,SOD23	
IG	KST06	SAMS	ngn	V _{сво} =80 B; I _c =500 мA; P _o =350 мВт; h ₂₁ >50; f _T >100 МГц	SOT23.SOD23	B-E-C
1G	MMBTA06	VISH	npn	V _{сво} =80 B; I _C =300 мA; P _D =350 мВт; h ₂₁ >50; f _T >100 МГц	SOT23,SOD23	
1G	MMBTA06	MOT	non	V _{DB0} =80 B; I _C =300 мA; P _D =350 мВт; h _{P1} >50; f _T >100 МГц	SOT23.SOD23	100000000000000000000000000000000000000
1G	TMPTA06	ALLEG	npn	V _{GB0} =80 B; I _{CB0} <100 нА; h ₂₁ >50; V _{CErsat} <0.25 B; f _T >100 МГц	SOT23,SOD23	B-E-C
1G-	BC847CW	PHIL	ngn	V _{CR0} =50 B; I _C =100 MA; P _D =200 MBT; h _{P1} =420800; f _T >100 MFu	SOT323,SC70	
1G-	BC847CW	PHIL	non	V _{CBO} =50 B; I _C =100 мА; P _D =200 мВт; h _{P1} =420800; f _T >100 МГц	S0T323,SC70	
1Go	BC847C	PHIL	npn	V _{CBO} =50 B; I _C =100 MA; P _D =250 MBr; h _{Pl} =420800; f _T >100 MFu	SOT23,SOD23	
IGR	BC847CR	PHIL	npn	V _{CB0} =45B; I _C =100 MA; P _D =310 MBr; h _{P1} =600; f _T >300 MFu	SOT23,SOD23	
1Gs	BC847C	INF	non	V _{G80} =50 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =420800; f _T =250 МГц	SOT23,SOD23	100000000000000000000000000000000000000
IGs	BC847CT	INF	npn	V _{CR0} =50 B; I _C =100 MA; P _D =350 MB1; N ₂₁ =420800; f ₁ =250 MFц	SOT416,SC75A	1200001120
1Gs	BC847CW	INF	non	000	SOT323.SC70	USSIA DA
1Gt	BC847CW	PHIL	7.0	V _{C80} =50 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =420800; f _T =250 MFu	SOT23,SOD23	100,000
		_	npn	V _{CB0} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =420800; f _T >100 МГц		
1Gt	BC847CW	PHIL	npn	V _{CB0} =50 B; I _C =100 мA; P _D =200 мBτ; h ₂₁ =420800; f _T >100 MΓц	SOT323,SC70	
1GT	SOA06	STM	npn	V _{C80} =80 B; I _C =500 мA; P _D =350 мВт; h ₂₁ >50; f _T >100 МГц	SOT23,SOD23	
1GZ	BC847C	ZETEX	npn	V _{C80} =50 B; I _C =100 мA; P _D =330 мВт; h ₂₁ =420800; f _T >300 МГц	SOT23,SOD23	70070070
1H	2SK123	PAN	nFET	V _{DS} >20 B; I _D =2 mA; P _D =200 mBt; g _E >0.7 mCm	SOT23,SOD23	7,000,00
1H	BC847	CDIL	npn	V _{C80} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =110800; f _T >100 МГц	SOT23,SOD23	13232 36
1H	FMMTA05	ZETEX	npn	V _{CB0} =60 B; I _C =500 мA; P ₀ =330 мВт; h ₂₁ >50; f _T >100 МГц	SOT23,SOD23	
1H	IRLML5203	IR	pMOS	HEXFET; V _{DS} =30 B; I _D =2.4A; P _D =1.25 BT; R _{DS(on)} <0.165 OM	SOT23,SOD23	
1H	KST05	SAMS	npn	V_{C80} =60 B; I_C =500 mA; P_D =350 mBT; $h_{21}>50$; $f_T>100 MFu$,	SOT23,SOD23	B·E·C
1H	MMBTA05	VISH	npn	V_{CB0} =60 B; I_C =30 mA; P_D =350 mBT; h_{21} >50; f_T >100 M Γ_{II}	SOT23,SOD23	B·E·C
1H	MMBTA05	MOT	npn	V_{C80} =60 B; I_C =30 мA; P_D =350 мВт; h_{21} >50; f_T >100 МГц	SOT23,SOD23	B-E-C
1H	TMPTA05	ALLEG	npn	V_{CB0} =60 B; I_{CB0} <100 HA; h_{21} >50; $V_{CE(sat)}$ <0.25 B; f_T >100 MFu,	SOT23,SOD23	B-E-C
1H-	BC847W	PHIL	npn	V_{C80} =50 B; I_C =100 mA; P_D =200 mBt; h_{21} =110800; f_T >100 MFu,	SOT323,SC70	B-E-C
1Hp	BC847	PHIL	npn	V_{C80} =50 B; I_C =100 mA; P_D =250 mBr; h_{21} =110800; f_T >100 M Γ_{IJ}	SOT23,SOD23	B-E-C
1Ht	BC847	PHIL	npn	V_{C80} =50 B; I_C =100 mA; P_D =250 mBt; h_{21} =110800; f_T >100 M Γ_{II}	SOT23,SOD23	B·E·C
1Ht	BC847W	PHIL	npn	V_{C80} =50 B; I_C =100 MA; P_0 =200 MBT; h_{21} =110800; f_T >100 MF $_{\rm LL}$	SOT323,SC70	B-E-C
1HT	SOA05	SGS	npn	V_{CB0} =60 B; I_C =500 mA; P_D =625 mBt; h_{21} >100; f_T >100 M Γ_{II}	SOT23,SOD23	B-E-C
IJ	BC848A	CDIL	npn	V _{сво} =30 B; I _C =100 мА; P _D =150 мВт; h ₂₁ =110220; f _T >300 МГц	SOT23,SOD23	B·E·C
1J	BC848A	TOSH	npn	V _{CB0} =30 B; I _C =100 MA; P _D =150 MBT; h _{P1} =110220; f _T =300 MFu	SOT23,SOD23	B·E·C
1J	BC848A	DIODS	npn	V _{CB0} =30 B; I _C =100 MA; P _D =300 MBT; h ₂₁ =110220; f _T =300 MFu,	SOT23,SOD23	B·E·C
1J	BC848A	VISH	npn	V _{CR0} =30 B; I _C =100 mA; P _D =310 mBr; h _{Pl} =110220; f _T >300 MFu	SOT23,SOD23	B·E·C
IJ	BC848AF	PHIL	npn	V ₀₈₀ *30B; I ₀ *100 мA; P ₀ *250 мВт; h ₂₁ *110220; f _T >100 МГц	SOT490.SC89	
1J	BC848ALT1	MOT	ngn	V _{csn} =30B; I _c =100 мA; P _n =300 мВт; h _{P1} =110220; f _T >100 МГц	SOT23,SOD23	SA HAROLINA
IJ	BC848AW	PHIL	npn	V _{CR0} =30B; I _C =100 мA; P _D =200 мВт; h _{P1} =110220; f _T >100 МГц	S0T323.SC70	100/04/193
1J	BC848AWT1	LRC	npn	V ₀₈₀ =30 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =110220; f _T >100 МГц	SOT323,SC70	1200000000
1J	BC848AWT1	ON	ngn	V _{C80} =30 B; I _C =100 mA; P _D =200 mBT; h ₂₁ =110220; f _T >100 mFu	SOT323,SC70	
1J	FMMT2369	ZETEX	npn	V _{GR0} =40 B; I _C =200 mA; P _D =330 mBr; h ₂₁ =40120	SOT23,SOD23	
1J	PMST2369	PHIL	npn	V _{CBB} =40 B; I _C =500 mA; P _B =300 mBr; h _{P1} =40120	SOT323,SC70	
IJA	MMBT2369ALT1	MOT	npn	V _{C80} =40 B; I _C =200 MA; P _D =200 MB; h ₂₁ =40120	SOT23,SOD23	
IJA IJp	BC848A	PHIL	npn	V _{CB0} =40 B; I _C =200 MA; P _D =300 MB1; H ₂₁ >40 V _{CB0} =30 B; I _C =100 MA; P _D =250 MB1; H ₂₁ =110220; f _T >100 MFu	SOT23,SOD23	
IJR	BC848AR	PHIL	nan	V_{CR0}^{-3} 0B; I_C^{-1} 100 MA; P_0^{-2} 300 MB1; n_{21}^{-1} 110220; $f_T>$ 100 MFu	SOT23,SOD23	0.0000000000000000000000000000000000000
IJR IJs	BC848A	INF	100		SOT23,SOD23	120000 100
			npn	V _{C80} =30B; I _C =100 mA; P _D =330 mBr; h ₂₁ =110220; f _T =250 MFu		
1Js	BC848AT	INF	npn	V _{CB0} =30 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =110220; f _T =250 MFu	SOT416,SC75A	
1Js	BC848AW	INF	npn	V _{C80} =30 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =110220; f _T =250 МГц	SOT323,SC70	
1Jt	BC848A	PHIL	npn	V _{CB0} =30 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =110220; f _T >100 МГц	SOT23,SOD23	
1JZ	BC848A	ZETEX	npn	V _{G80} =30 B; I _C =100 мA; P _D =330 мВт; h ₂₁ =110220; f _T >300 МГц	SOT23,SOD23	
1K	BC848B	CDIL	npn	V _{GB0} =30 B; I _C =100 мA; P _D =310 мВт; h ₂₁ =200450; f _T >300 МГц	SOT23,SOD23	100000000000000000000000000000000000000
IK	BC848B	TOSH	npn	V _{CB0} =30 B; I _C =100 mA; P _D =150 mBt; h ₂₁ =200450; f _T =300 MFu	SOT23,SOD23	B·E·C





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
IK E	BC848B	DIODS	non	V _{CR0} =30 B; I _C =100 mA; P _D =300 mBT; h ₂₁ =200450; f _T =300 MFu,	SOT23,SOD23	B-E-C
IK E	BC848B	VISH	non	V _{CR0} =30 B; I _C =100 мА; P _D =310 мВт; h ₂₁ =200450; f _T >300 МГц	SOT23,SOD23	B·E·C
_	BC848B	ZETEX	non	V _{CR0} =30 B; I _C =100 мА; P _D =330 мВт; I _{D2} =200450; f _T >300 МГц	SOT23,SOD23	
IK E	BC848B	ITT	non	V _{CR0} =30 B; I _C =100 mA; P _D =330 mBT; h ₂₁ =200450; f _T >300 MFц	SOT23.SOD23	B·E·C
_	BC848BF	PHIL	non	V _{CB0} =30 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ =200450; f _T > 100 МГц	SOT490,SC89	
IK E	BC848BLT1	MOT	non	V _{CR0} =30 B; I _C =100 мА; P _D =300 мВт; h ₂₄ =200450; f _T >100 МГц	SOT23 SOD23	100000000000000000000000000000000000000
IK E	BC848BW	PHIL	non	V _{CR0} =30 B; I _C =100 мА; P _D =200 мВт; I _{D1} =200450; f _T >100 МГц	S0T323,SC70	B·E·C
	BC848BWT1	LRC	non	V _{CR0} =30 B; I _C =100 mA; P _D =250 mBT; h ₂₁ =200450; f _T =250 MFu	SOT323,SC70	
_	BC848BWT1	ON	non	V _{CR0} =30 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =200450; f _T =250 MFц	SOT323,SC70	
_	FMMT4400	ZETEX	non	V _{CB0} =60B; I _C =600MA; P _D =330MBT; I _D =50150; f _T >200MFu	SOT23,SOD23	
_	KST6428	SAMS	non	V _{CR0} =60 B; I _C =200 MA; P _D =350 MBT; h ₂₁ =250650; f _T =100700 MFu	SOT23,SOD23	
	MMBT6428	MOT	non	V _{CR0} =60 B; I _C =200 MA; P _D =300 MBτ; I _D 1=250650; f _T >100 MΓ ₄	SOT23,SOD23	
	PMST6428	PHIL	non	V _{CB0} =60 B; I _C =200 MA; P _D =300 MB1; II ₂ 1=250650; f _T =100700 MF ₄	S0T323,S0D23	0.0000000000
	DOUGH STATE OF THE PARTY OF THE			000		2000
	2SK316P	PAN	nFET	V _{6S} =10B; I _D =5MA; P _D =200 MBT; g _F >15MCM; I _{DSS} =516MA	SOT23,SOD23	
-	BC848B	PHIL	npn	V _{CB0} =30 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =200450; f _T > 100 МГц	SOT23,SOD23	
_	2SK316Q	PAN	nFET	V _{BS} =10B; I _D =5MA; P _D =200 MBT; g _F >15MCM; I _{DSS} =1424MA	SOT23,SOD23	
_	BC848BR	PHIL	npn	V _{C80} =30 B; I _C =100 мA; P _D =310 мВт; h ₂₁ =330; f _T >300 МГц	SOT23,SOD23	
	BC848B	INF	npn	V _{CB0} =30 B; I _C =100 mA; P _D =330 mBT; h ₂₁ =200450; f _T =250 MFu	SOT23,SOD23	
	BC848BT	INF	npn	V _{GB0} =30 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ =200450; f _T =250 МГц	S0T416,SC75A	
	BC848BW	INF	npn	V _{CB0} =30 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ =200450; f ₁ =250 МГц	S0T323,SC70	
	BC848B	PHIL	npn	V _{CB0} =30 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ =200450; f _T > 100 МГц	SOT23,SOD23	
ikz F	FMMT4400	ZETEX	npn	V_{CB0} =60 B; I_C =600 mA; P_D =330 mBT; h_{21} =50150; f_T >200 M Γ_{IJ}	SOT23,SOD23	B·E·C
IL E	BC848C	ITT	npn	V_{CB0} =30B; I_C =100mA; P_D =310mBT; h_{21} =420800; f_T >300MFu	SOT23,SOD23	B·E·C
IL E	BC848C	CDIL	non	V_{CB0} =30B; I_C =100mA; P_D =310mBT; h_{21} =420800; f_T >300M Γ_U	SOT23,SOD23	B·E·C
L E	BC848C	DIODS	npn	V _{CB0} =30 B; I _C =100 мА; P _D =300 мВт; h ₂₁ =420800; f _T =300 МГц	SOT23,SOD23	B·E·C
IL E	BC848C	TOSH	non	V _{CB0} =30 B; I _C =100 mA; P _D =150 mBT; h ₂₁ =420800; f _T =300 MFu	SOT23,SOD23	B·E·C
IL E	BC848C	VISH	npn	V _{CB0} =30 B; I _C =100 мА; P _D =310 мВт; h ₂₁ =420800; f _T >300 МГц	SOT23,SOD23	B·E·C
IL E	BC848CF	PHIL	npn	V _{CB0} =30 B; I _C =100 мА; P ₀ =250 мВт; h ₂₁ =420800; f _T >100 МГц	SOT490,SC89	B·E·C
IL E	BC848CLT1	MOT	npn	V _{CB0} =30 B; I _C =100 мА; P ₀ =300 мВт; h ₂₁ =420800; f _T >100 МГц	SOT23,SOD23	B·E·C
IL E	BC848CW	PHIL	non	V _{CR0} =30 B; I _C =100 MA; P _D =200 MBT; h ₂₁ =420800; f _T >100 MFu	SOT323,SC70	B·E·C
IL E	BC848CWT1	LRC	non	V _{CB0} =30 B; I _C =100 mA; P _D =250 mBT; h ₂₁ =420800; f _T =250 MFц	SOT323,SC70	B·E·C
L E	BC848CWT1	ON	non	V _{CB0} =30 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =420800; f _T =250 MFц	S0T323.SC70	B·E·C
L F	FMMT4401	ZETEX	non	V _{CR0} =60 B; I _C =600 мА; P _D =330 мВт; I _{D1} =100300; f _T >250 МГц	SOT23,SOD23	B·E·C
	MMBT6429	MOT	non	V _{CR0} =55B; I _C =200 MA; P _D =300 MBT; I _{D2} =5001250; f _T >100 MFu	SOT23.SOD23	
	PMST6429	PHIL	non	V _{CR0} =55 B; I _C =200 MA; P _D =200 MB; I _D =5001250; f _T =100700 MFu	SOT323,SC70	
	2SC4103M	ROHM	non	V _{CBO} *30B; I _C *30mA; P _D *200mBr; h ₂₁ *3982; f _T >110MFu	S0T323.SC70	
-	2SC4103N	ROHM	non	V _{CR0} =30 B; I _C =30 mA; P _D =200 mBτ; h ₂₁ =56120; f _T >110 MΓ _U	SOT323,SC70	
_	2SC4103P	ROHM	non	V _{CB0} -30B; I _C -30 мA; P _D -200 мBτ; h ₂₁ -82180; f _T >110 MΓц	S0T323.SC70	
-	2SK247P	PAN	nFET	V _{RS} =15B; I _D =20 mA; P _D =150 mBr; Q _F >3 mCm; I _{DSS} =0.51.5 mA	SOT23.SOD23	200000000000000000000000000000000000000
	100000000000000000000000000000000000000	-		00 10 0 0 00		
-	BC848C	PHIL	npn	V _{CB0} -30 B; I _C =100 MA; P _D =250 MBτ; h ₂₁ =420800; f _T >100 MΓц	SOT23,SOD23	
_	2SC4103Q	ROHM PAN	npn	V _{CB0} =30 B; I _C =30 MA; P _D =200 MBT; h ₂₁ =120270; f _T >110 MFц	SOT323,SC70	
	2SK247Q		nFET	V _{SS} =15B; I _D =20 MA; P _D =150 MBT; g _F >3 MCM; I _{DSS} =13 MA	SOT23,SOD23	
	2SK247P	PAN	nFET	V _{GS} =15B; I _D =20 MA; P _D =150 MBT; g _F >3 MCM; I _{DSS} =26 MA	SOT23,SOD23	0.0100 - 010
	BC848CR	PHIL	npn	V _{CB0} =30 B; I _C =100 мA; P _D =310 мВт; h ₂₁ =600; f _T >300 МГц	SOT23,SOD23	
	2SK247S	PAN	nFET	V _{GS} =15B; I _D =20mA; P _D =150 mBr; g _F >3 mCm; I _{DSS} =412mA	SOT23,SOD23	
	BC848C	INF	npn	V _{CB0} =30 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =420800; f _T =250 МГц	SOT23,SOD23	
	BC848CT	INF	npn	V _{CB0} =30 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =420800; f ₁ =250 МГц	S0T416,SC75A	
-	BC848CW	INF	npn	V _{CB0} =30 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =420800; f _T =250 МГц	S0T323,SC70	
	BC848C	PHIL	npn	V_{CB0} =30B; I_C =100mA; P_D =250mBT; h_{21} =420800; f_T >100M Γ_{II}	SOT23,SOD23	
M E	BC848	CDIL	npn	V _{CB0} =30 B, I _C =100 мА; P _D =250 мВт; h ₂₁ =110800; f _T >100 МГц	SOT23,SOD23	B·E·C
M E	BC848C	DIODS	npn	V _{CB0} =30 B; I _C =100 мА; P _D =300 мВт; h ₂₁ =420800; f _T =300 МГц	SOT523	B-E-C
IM F	FMMTA13	ZETEX	non	V _{CR0} =40 B; I _C =300 mA; P _D =330 mBT; h ₂₁ >10000	SOT23,SOD23	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
IM	KST13	SAMS	npn	V _{C80} ±30 B; I _C =300 мA; P _D =350 мВт; h ₂₁ >5000; f _T >125 МГц	SOT23,SOD23	B-E-C
IM	MMBTA13	VISH	dnpn	V _{C80} +30B; I _C +300 мА; P _D +350 мВт; h _{Pl} <10000; f _T <125 МГц	SOT23,SOD23	B·E·C
IM	MMBTA13LT1	MOT	dnpn	V ₀₈₀ =30 B; I _C =300 мА; P _D =300 мВт; h ₂₁ >5000; f ₁ >125 МГц	SOT23,SOD23	B-E-C
1M-	BC848W	PHIL	non	V _{CR0} =30B; I _C =100 MA; P _D =200 MBT; h _{P1} =110800; f _T >100 MFu	SOT323.SC70	B-E-C
1MN	2SC4128N	ROHM	npn	V _{CR0} =40 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =56120; f _T >230 МГц	SOT323,SC70	
IMP	2SC4128P	ROHM	npn	V _{CB0} =40 B; I _C =100 мA; P _D =200 мВт; h ₂₁ =82180; f _T >230 МГц	SOT323.SC70	100000000000000000000000000000000000000
1MP	2SJ84P	PAN	pFET	V _{ns} =15 B; I _n =10 mA; P _n =200 mBr; Q _e =9 mCm	SOT23,SOD23	D·S·G
1Mp	BC848	PHIL	non	V _{G80} =30 B; I _G =100 mA; P _D =250 mBt; h ₂₁ =110800; f _T >100 MFu	SOT23,SOD23	
1MQ	2SJ84Q	PAN	pFET	V _{DS} = 15 B; I _D =10 mA; P _D =200 mBr; g _F =9 mCm	SOT23,SOD23	
IMR	2SJ84R	PAN	pFET	V _{DS} = 15 B; I _D =10 MA; P _D =200 MB;; Q _E =9 MCM	SOT23,SOD23	
1Mt	BC848W	PHIL	npn	V _{CR0} =30 B; I _C =100 MA; P _D =200 MBT; h _{Pl} =110800; f _T >100 MFu	SOT323,SC70	
IN.	FMMTA14	ZETEX	nan	V _{C80} =40 B; I _C =300 mA; P _D =330 mBt; h ₂₁ >20000	SOT23.SOD23	
1N	KST14	SAMS	npn	V_{C80} =30 B; I_C =300 MA; P_D =350 MBT; h_{21} >10000; f_T >125 M Γ L,	SOT23,SOD23	1000001130
1N	MMBT3904	VISH	ngn	V _{C80} =50 B; I _C =300 MA; P _D =300 MB1; N ₂₁ >10000; I _T >120 MF _L V _{C80} =60 B; I _C =100 MA; P _D =200 MBT; N ₂₁ =100300; I _T >300 MF _L	SOT23,SOD23	1800 /A DA
1N	MMBTA14	VISH	1		SOT23,SOD23	100,000
IN		_	dnpn	V _{C80} =30 B; I _C =300 xA; P _D =350 xBt; h ₂₁ < 20000; f ₁ < 125 MFu		
_	MMBTA14LT1	MOT	dnpn	V _{C80} =30 B; I _C =300 MA; P _D =300 MBt; h ₂₁ >10000; f _T >125 MFu	SOT23,SOD23	
IN	TMPTA14	ALLEG	npn	V _{CB0} =30 B; I _{CB0} <100 HA; h ₂₁ >20 κ; V _{CE(sat)} <1.5 B; f _T >125 MΓц	SOT23,SOD23	
IN5	ZTX11N15DF	ZETEX	npn	V _{G80} -15B; I _G -3A	SOT23,SOD23	7007070
IOP	2SK662P	PAN	nFET	V _{DS} =30 B; I _D =20 mA; P _D =150 mBt; g _F >4 mCm; I _{DSS} =0.53 mA	SOT323,SC70	100001 000
10Q	2SK662Q	PAN	nFET	V _{DS} =30 B; I _D =20 мА; P _D =150 мВт; Q _F >4 мСм; I _{DSS} =26 мА	SOT323,SC70	100000000000000000000000000000000000000
IOR	2SK662R	PAN	nFET	V _{DS} =30 B; I _D =20 мA; P _D =150 мВт; Q _F >4 мСм; I _{DSS} =412 мА	SOT323,SC70	
IP.	FMMT2222A	ZETEX	npn	V _{CB0} =75B; I _C =600 мA; P _D =330 мВт; h ₂₁ =120360; f _T >300 МГц	SOT23,SOD23	
IP	KST2222A	SAMS	npn	V_{CB0} =75B; I_C =600 mA; P_D =350 mBT; h_{21} >75; f_T >300 MFu,	SOT23,SOD23	B·E·C
IP	MBT2222A	TOSH	npn	V_{CB0} =75B; I_C =600 mA; P_D =250 mBT; h_{21} >40; f_T =300 MFu,	SOT23,SOD23	B·E·C
IP	MMBT2222A	VISH	npn	V_{080} =50 B; I_0 =800 mA; P_0 =200 mBt; h_{21} =100300; f_T >200 M Γ_{II}	SOT23,SOD23	B-E-C
IP	MMBT2222ALT1	MOT	npn	V _{CB0} =75 B; I _C =600 мA; P _D =300 мВт; h ₂₁ >35; f _T >300 МГц	SOT23,SOD23	B-E-C
IP	MMBT2222LT1	ON	npn	V _{CB0} =60 B; I _C =600 мА; P _D =225 мВт; h ₂₁ >30	SOT23,SOD23	B-E-C
1P	TMPT2222A	ALLEG	npn	V _{CB0} =75B; I _{CB0} <10 HA; h ₂₁ =100300; V _{CE(sat)} <0.3B; f ₇ >250 MFu	SOT23,SOD23	B-E-C
-1P	PMST2222A	PHIL	npn	V _{CB0} =75 B; I _C =600 мA; P _D =200 мВт; h ₂₁ =100300; f _T >300 МГц	SOT323,SC70	B·E·C
1Q	FMMT5088	ZETEX	npn	V _{CB0} =35B; I _C =50 MA; P _D =330 MBT; h ₂₁ =300900; f _T >50 MFu	SOT23,SOD23	B-E-C
1Q	KST5088	SAMS	npn	V _{CB0} =35 B; I _C =50 мA; P _D =350 мВт; h ₂₁ =300900; f _T >50 МГц	SOT23,SOD23	B-E-C
1Q	MMBT5088	VISH	npn	V _{DB0} =35 B; L _C =100 мA; P _D =350 мВт; h _{P1} =300900; f _T >50 МГц	SOT23,SOD23	B-E-C
IQ	MMBT5088	MOT	npn	V _{GB0} =30 B; I _G =100 MA; P _D =350 MBT; h _{P1} =3501400; f _T >50 MFц	SOT23,SOD23	B-E-C
IQ.	TMPT5088	ALLEG	npn	V _{G80} =35B; I _{G80} <50 HA; h ₂₁ =300900; V _{GE(sat)} <0.5B	SOT23.SOD23	B-E-C
IR.	FMMT5089	ZETEX	npn	V _{CB0} =30 B; I _C =50 MA; P _D =330 MBT; h _D =4001200; f _T >50 MFц	SOT23,SOD23	
1R	KST5089	SAMS	non	V ₀₈₀ =35 B; I _C =50 мA; P _D =350 мВт; h ₂₁ =4001200; f _T >50 МГц	SOT23.SOD23	
1R	MMBT5089	VISH	npn	V _{CR0} =30 B; I _C =100 мA; P _D =350 мВт; h _{P1} =4001200; f _T >50 МГц	SOT23,SOD23	50700000
IR.	MMBT5089	MOT	npn	V _{C80} =25B; I _C =100 мA; P _D =350 мВт; h ₂₁ =4501800; f ₁ >50 МГц	SOT23,SOD23	100,000,000
IR.	TMPT5089	ALLEG	npn	V _{CB0} =30B; I _{CB0} <50HA; h ₂₁ =4001200; V _{CEIsst1} <0.5B	SOT23,SOD23	
IS	MMBT2369A	FAIR	npn	V _{C80} =40 B; I _C =200 mA; P _D =225 mBT; h ₂₁ >40	SOT23,SOD23	
IS	MSC3130	MOT	non	V _{CR0} =10B; f _T =1.4ΓΓц	SOT346.SC59	
ISP	2SC3130P	PAN	npn	V _{CBO} =15B; I _C =50мA; P _D =150 мВт; h ₂₁ =75130; f _T =1.9 ГГц	SOT23,SOD23	
ISP	2SC3935P	PAN	npn	V ₆₈₀ =15B; I ₀ =50 мА; Р ₀ =150 мВт; h ₂₁ =75130; I ₁ =1.9 ГГц	SOT323,SC70	
ISP	2SC4809P	PAN	non	V _{C80} =15 B; I _C =50 мA; P _D =150 мBт; I _{P1} =75150; I _T =1.911ц V _{C80} =15 B; I _C =50 мA; P _D =125 мBт; I _{P1} =75130; I _T =1.42.7 ГГц	SOT416,SC75A	
ISQ	2SC3130Q	PAN		V _{CR0} =15B; I _C =50MA; P _D =125MBT; I _{D1} =75130; I _T =1.42.711I _L V _{CR0} =15B; I _C =50MA; P _D =150MBT; I _{D1} =110220; I _T =1.9IT _L	SOT23,SOD23	100000000000000000000000000000000000000
	11.10.10.10.00.1022E	PAN	npn		SOT323,SOD23	
ISQ	2SC3935Q		npn	V _{C80} =15B; I _C =50 mA; P _O =150 mBr; h ₂₁ =110220; f _T =1.9TT _U		100.000
ISQ	2SC4809Q	PAN	npn	V _{C80} =15B; I _C =50 мA; P _O =125 мBr; h ₂₁ =110220; f _T =1.42.7 ГГц	SOT416,SC75A	
ISR	2SC4809R	PAN	npn	V _{C80} =15B; I _C =50 MA; P _D =125 MBT; h ₂₁ =200400; f _T =1.42.7 ITu	SOT416,SC75A	
IT	2SC3933T	PAN	npn	V_{CB0} =30 B; I_C =20 mA; P_D =150 mBT; h_{21} =40200; f_T >750 MF $_{II}$	SOT323,SC70	
IT1	MMST5101	ROHM	pnp	V _{CB0} =60 B; I _C =200 мА; h ₂₁ =200400; f _T >125 МГц	SOT23,SOD23	
IT1	SST5101	ROHM	pnp	V_{CB0} =60 B; I_C =200 mA; h_{21} =200400; f_T >125 MFu	SOT346,SC59	
IU	2SC3110	PAN	npn	$V_{CB0}=15B$; $I_C=50$ mA; $P_D=200$ mBT; $h_{21}>40$; $f_7=4.5$ FT μ	SOT23,SOD23	B.E.C





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
10	2SC3934	PAN	npn	V _{CBO} =15B; I _C =50 mA; P _D =150 mBT; h ₂₁ >40; f _T =4.5 FFu	SOT323,SC70	B·E·C
10	KST2484	SAMS	npn	V _{CBD} =60 B; I _C =50 mA; P _D =350 mBT; h ₂₁ >250	SOT23,SOD23	B·E·C
10	MMBT2484LT1	MOT	npn	V _{CB0} =60 B; I _C =200 mA; P _D =225 mBT; h ₂₁ >250	SOT23,SOD23	B·E·C
1V	BF820	CDIL	npn	V _{CR0} =300B; I _C =50mA; P _D =250mBT; h ₂₁ >50; f _T >60 MFu	SOT23,SOD23	B·E·C
1V	MMBT6427	MOT	dnpn	V _{CR0} =40 B; I _C =500 mA; P _D =225 mBT; h ₂₁ >10000	SOT23,SOD23	E·B·C
1V	TMPT6427	ALLEG	non	V _{CB0} =40 B; I _{CB0} <50 нA; h ₂₁ =10000100000; V _{CE(sat)} <1.2 B; f _T >130 МГц	SOT23,SOD23	B·E·C
1V-	BF820W	PHIL	non	V _{CR0} =300 B; I _C =100 MA; P _D =200 MBT; h ₂₁ >50; f ₇ >60 MFu	SOT323,SC70	B-E-C
1Vo	BF820	PHIL	non	V _{CR0} =300 B; I _C =50 mA; P _D =250 mBT; h ₂₁ >50; f _T >60 MFu	SOT23,SOD23	B-E-C
1VR	2SD1149R	PAN	non	V _{CR0} =100B; I _C =20MA; P _D =200MBT; h ₂₁ =400800	SOT346,SC59	B·E·C
1VR	2SD1824R	PAN	non	V _{CBO} =100 B; I _C =50 MA; P _D =150 MBr; h _{C1} =400800; f _T =90 MFu	SOT323,SC70	
IVS	2SD1149S	PAN	non	V _{CP0} =100B; I _C =20mA; P ₀ =200mBT; h ₂₁ =6001200	SOT346.SC59	
IVS	2SD1824S	PAN	non	V _{CR0} =100B; I _C =50mA; P _D =150mBr; h ₂₁ =6001200; f _T =90MFu	SOT323.SC70	-0.075.000
1VT	2SD1149T	PAN	non	V _{CB0} =100 B; I _C =20 mA; P _D =200 mBr; h ₂₁ =8002000	SOT346.SC59	C22/00000 2722
1VT	2SD1824T	PAN	non	V _{CR0} =100B; I _C =20MA; P _D =250MBT; I _C =10002000; I _T =90 MFµ	S0T323.SC70	200000000000000000000000000000000000000
1Vt	BF820	PHIL	non	V _{CB0} -100B, I _C -300MA, P _D -130MBT, I _D -10002000, I _T -30MFL V _{CB0} -300B; I _C -50MA; P _D -250MBT; I _D -50; f _T >50; f _T >60 MFL	SOT23 SOD23	Control of the contro
1Vt	BF820W	PHIL	non	V _{CB0} -300 B; I _C -301MA; P _D -230 MBT; I ₂₁ >50; I ₇ >60 MFц	S0T323,SC70	
1W	BF821	CDIL			SOT23.SOD23	
IW			pnp	V _{CB0} =300B; I _C =50 MA; P _D =250 MBT; h ₂₁ >50; f _T >60 MFu		
0.00	FMMT3903	ZETEX	npn	V _{CB0} =60 B; I _C =200 MA; P _D =330 MBT; h ₂₁ =50150; f _T >250 MF _U	S0T23,S0D23	- C. C. C. C.
1W-	BF822W	PHIL	npn	V_{CB0} =250 B; I_C =50 MA; P_D =250 MBT; h_{21} >50; f_T >60 MFL	S0T323,SC70	70070070
1Wp	BF821	PHIL	pnp	V_{CB0} =300B; I_C =50mA; P_D =250mBT; h_{21} >50; f_T >60 M Γ_{LL}	SOT23,SOD23	120.00 00
1Wt	BF821	PHIL	pnp .	V _{CB0} =300 B; I _C =50 мА; P _D =250 мВт; h ₂₁ >50; f ₁ >60 МГц	SOT23,SOD23	
1Wt	BF822W	PHIL	npn	V _{CB0} =250 B; I _C =50 мA; P ₀ =250 мВт; h ₂₁ > 50; f _T >60 МГц	SOT323,SC70	
1X	BF822	CDIL	npn	V _{сво} =250 B; I _C =50 мА; P _D =250 мВт; h ₂₁ > 50; f _T > 60 МГц	SOT23,SOD23	
1X	MMBT930L	MOT	non	V_{CB0} =45B; I_C =30 mA; P_D =225 mBT; h_{21} =100300; f_T >30 MFu	SOT23,SOD23	B·E·C
1Xp	BF822	PHIL	npn	V _{CB0} =250 B; I _C =50 мA; P _D =250 мВт; h ₂₁ >50; f _T >60 МГц	SOT23,SOD23	B.E.C
1Xt	BF822	PHIL	npn	V_{CB0} =250 B; I_C =50 mA; P_D =250 mBr; h_{21} >50; f_T >60 MFu	SOT23,SOD23	B.E.C
1Y	BF823	CDIL	pnp	V _{CB0} =250 B; I _C =50 мA; P _D =250 мВт; h ₂₁ >50; f _T >60 МГц	SOT23,SOD23	B·E·C
1Y	KST3903	SAMS	pnp	V _{CB0} =60 B; I _C =200 мА; P _D =350 мВт; h ₂₁ =50150; f _T >250 МГц	SOT23,SOD23	B·E·C
17	MMBT3903	MOT	npn	V _{CB0} =60 B; I _C =200 mA; P _D =350 mBT; h ₂₁ >15	SOT23,SOD23	B·E·C
1Yp	BF823	PHIL	pnp	V _{CB0} =250 B; I _C =50 мА; P _D =250 мВт; h ₂₁ >50; f _T >60 МГц	SOT23,SOD23	B.E.C
1Yt	BF823	PHIL	pnp	V _{CB0} =250 B; I _C =50 мA; P _D =250 мВт; h ₂₁ >50; f ₁ >60 МГц	SOT23,SOD23	B·E·C
1Z	BAS7006	ZETEX	shd×2	V _R <70B; V _E (I _F =1 MA)<0.41B; I _R <0.2 MKA; C _D <2.0 mΦ	SOT23,SOD23	K1-K2-A1,A2
1Z	BAS70-06	ZETEX	shd×2	V _B <70B; I _E <70 MA; V _E (I _E =1 MA)<410 MB; C _D <2 nΦ	SOT23,SOD23	K1-K2-A1,A2
1Z	MMBT6517	MOT	non	V _{сво} =350 B; I _c =500 мА; P _D =300 мВт; h ₂₁ =20200; f _T >40 МГц	SOT23,SOD23	B·E·C
1ZR	2SD1030R	PAN	non	V _{CR0} =50 B; I _C = 100 mA; P _D =200 mBT; h ₂₁ =400800	SOT346.SC59	B·E·C
1ZR	2SD1823R	PAN	non	V _{CR0} =50 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =400800; f _T =120 МГц	S0T323.SC70	B·E·C
1ZR	2SD2345R	PAN	non	V _{CP0} =50 B; I _C =100 mA; P _D =125 mBT; h ₂₁ =400800; f _T =120 MFu	SOT416.SC75A	B·E·C
IZS	2SD1030S	PAN	non	V _{CR0} =50B; I _C =100mA; P _D =200mBr; h ₂₁ =6001200	SOT346.SC59	100 000000
1ZS	2SD1823S	PAN	non	V _{CBO} =50 B; I _C =50 мА; P _D =150 мВт; h ₂₁ =6001200; f _T =120 МГц	SOT323.SC70	20000000
1ZS	2SD2345S	PAN	non	V _{CR0} =50 B; I _C = 100 mA; P _D =125 mBτ; h _{Cl} =6001200; f _T =120 MΓц	SOT416.SC75A	
1ZT	2SD1030T	PAN	non	V _{CR0} =50B; I _C =100MA; P _D =200MBT; h ₂₁ =10002000	S0T346,SC59	
1ZT	2SD1823T	PAN	non	V _{CR0} =50 B; I _C =50 мA; P _D =150 мBт; I _{P2} =10002000; f _T =120 МГц	S0T323.SC70	
1ZT	2SD2345T	PAN	non	V _{CB0} =50 B; I _C =100 MA; P _D =125 MBT; I _{D1} =10002000; I _T =120 MIQ V _{CB0} =50 B; I _C =100 MA; P _D =125 MBT; I _{D1} =10002000; I _T =120 MIQ	S0T416,SC75A	
2.0X	02CZ2.0	TOSH	dz.	V ₂ (I ₂₇ =5 mA)=1.852.15 B; I ₁ (V _R =0.5 B)<120 mKA;	S0T346,SC59	
			100000	Z _{ZT} (I _{ZT} =0.5mA)<1000 Om	100000000000000000000000000000000000000	
2.2X	02CZ2.2	TOSH	dz	V _Z (I _{ZT} =5 мA)=2.052.38 B; I _L (V _B =1.0 B)≤120 мкA; Z _{ZT} (I _{ZT} =0.5 мA)≤1000 0м	SOT346,SC59	A•n.c.•K
2.4X	02CZ2.4	TOSH	dz	V _Z (I _{ZT} =5 mA)=2.282.60 B, I _L (V _R =1.0 B)<120 mkA; Z _{ZT} (I _{ZT} =0.5 mA)<1000 0 m	SOT346,SC59	A•n.c.•K
2.7X	02CZ2.7	TOSH	dz	V _X (_{ZT} =5 mA)=2.50 , 2.90 B; I _L (V _B =1.0 B)<120 mkA; Z _{ZT} (I _{ZT} =0.5 mA)<1000 0 m	SOT346,SC59	A•n.c.•K
200	SSTPAD200	SIL	dl	V _R =55B; I _E <10 MA; V _E (I _E =1 MA) <1.5 B; I _R <200 πA; C _T <2 πΦ	SOT23,SOD23	K·K·A
20A	MMBZ20VAL	ON	dz×2	V _z (I _{zz} =1 mA)=1921 B; V _E (I _E =10 mA)<0.9 B	SOT23,SOD23	K1-K2-A1-A2

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
20p	BF545A	PHIL	nFET	V _{DS} =30 B; I _{DSS} =6.5 mA; P _D =250 mBT; g _F =36.5 mc	SOT23,SOD23	S·D·G
20t	BF545A	PHIL	nFET	V _{DS} =30 B; I _{DSS} =6.5 мА; Р _D =250 мВт, g _E =36.5 мс	SOT23,SOD23	S·D·G
20V	PZM20NB	PHIL	dz	V ₂ (I _{ZT} =5 mA)=18.8621.08B; Z _{ZT} (I _{ZT} =5 mA)<200m	SOT346,SC59	A•n.c.•K
20W	BF545A	PHIL	nFET	V _{ns} =30 B; I _{nss} =6.5 мА; Р _n =250 мВт; g _p =36.5 мс	SOT23,SOD23	S·D·G
20W	SO2222AW	SGS	npn	V _{CB0} =75B; I _C =800 мA; P _D =310 мВт; h ₂₁ =100300; f _T >250 МГц	SOT323,SC70	B·E·C
20X	02CZ20	TOSH	dz	V _Z (I _{ZT} =5 mA)= 18.8021.20B; I _L (V _R =15B)<0.5mcA; Z _{Z1} (I _{ZT} =0.5 mA)<200 OM	SOT346,SC59	A•n.c.•K
210	KTY82-210	PHIL	rts	T _{MMB} =-55150 °C; R ₂₅ =19802020 O _M	SOT23,SOD23	CONT1 - CONT2 - SUB
21p	BF545B	PHIL	nFET	V _{DS} =30 B; I _{DSS} =15 мА; Р _D =250 мВт; g _F =36.5 мс	SOT23,SOD23	S-D-G
21t	BF545B	PHIL	nFET	V _{DS} =30 B; I _{DSS} =15 мА, Р _D =250 мВт; g _F =36.5 мс	SOT23,SOD23	S-D-G
21W	BF545B	PHIL	nFET	V _{DS} =30 B; I _{DSS} =15 mA; P _D =250 mBr; Q _F =36.5 mc	SOT23,SOD23	S·D·G
22	DTC123EE	ROHM	Dnpn	V_{C80} =50 B; I_c = 100 x/A; P_0 =150 x/B; h_{21} >20; f_T >250 MFu; R_1/R_2 =2.2/2.2 x/Om	SOT416,SC75A	B-E-C
22	DTC123EKA	ROHM	Dnpn	V_{CB0} = 50 B; I_C = 100 MA; P_D = 200 MBT; h_{21} > 20; f_T > 250 MFu; R_1/R_2 = 2.2/2.2 KOM	SOT346,SC59	B-E-C
22	DTC123EUA	ROHM	Dnpn	V_{C80} = 50 B; I_C = 100 MA; P_D = 200 MB $_T$; h_{21} > 20; f_T > 250 M Γ u; P_T / P_Z = 2.2/2.2 KOM	SOT323,SC70	B·E·C
22	MMBT4209	MOT	pnp	V_{C80} =15B; I_C =50 mA; P_D =300 mBT; h_{21} >35; f_T =850 MFu	SOT23,SOD23	B-E-C
220	KTY82-220	PHIL	rts	T _{MMB} =-55150 °C; R ₂₅ =19602040 O _M	SOT23,SOD23	CONT1 · CONT2 · SUB
221	KTY82-221	PHIL	rts	T _{MMB} =-55150 °C; R ₂₅ =19602000 Ont	SOT23,SOD23	CONT1 · CONT2 · SUB
222	KTY82-222	PHIL	rts	T _{MMB} =-55150 °C; R ₂₅ =20002040 Ont	SOT23,SOD23	CONT1 · CONT2 · SUB
22p	BF545C	PHIL	nFET	V _{DS} =30 B; I _{DSS} =25 mA; P _D =250 mBT; g _E =36.5 mc	SOT23,SOD23	S·D·G
22t	BF545C	PHIL	nFET	V _{DS} =30 B; I _{DSS} =25 мА; Р _D =250 мВт; g _F =36.5 мс	SOT23,SOD23	S-D-G
22V	PZM22NB	PHIL	dz	V _Z (I _{ZT} =5 mA)=20.8823.17 B; Z _{ZT} (I _{ZT} =5 mA)<250m	SOT346,SC59	A·n.c.·K
22W	BF545C	PHIL	nFET	V _{DS} =30 B; I _{DSS} =25 mA; P _D =250 mBr; g _E =36.5 mc	SOT23,SOD23	S-D-G
22X	02CZ22	TOSH	dz	V _Z (I _{ZT} = 5 mA) = 20.8023.30B; I _L (V _R = 17 B) < 0.5 mA; Z _{ZT} (I _{ZT} = 0.5 mA) < 200 Om	SOT346,SC59	A·n.c.·K
23	DTC143EE	ROHM	Dnpn	V_{CB0} =50 B; I_C =100 MA; P_0 =150 MBT; h_{21} >20; f_T >250 MFu; R_1/R_2 =4.7/4.7 KOM	SOT416,SC75A	B-E-C
23	DTC143EKA	ROHM	Dnpn	V_{C80} =50 B; I_{c} =100 xA; P_{0} =200 xBr; h_{21} >20; f_{T} >250 MFu; R_{1}/R_{2} =4.7/4.7 xOx	SOT346,SC59	B-E-C
23	DTC143EUA	ROHM	Dnpn	$\begin{array}{l} V_{\rm CB0}\text{=}50B_1I_{\rm C}\text{=}100\text{mA;}P_0\text{=}200\text{mBT;}h_{21}\!>\!20;f_7\!>\!250\text{MFu;}\\ R_1/R_2\text{=}4.7/4.7\text{kOm} \end{array}$	SOT323,SC70	B•E•C
23	PDTA114TK	PHIL	Dpnp	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBt; h ₂₁ >200; R ₁ 10 kOm	SOT346,SC59	B-E-C
24	DTC114EE	ROHM	Dnpn	V _{C80} =50 B; I _C =100 мА; P ₀ =150 мВт; h ₂₁ >30; f ₁ >250 МГц; R ₁ /R ₂ =10/10 кОм	SOT416,SC75A	B-E-C
24	DTC114EKA	ROHM	Dnpn	V_{CB0} =50 B; I_C =100 mA; P_0 =200 mBT; h_{21} >30; f_7 >250 MFu; R_1/R_2 =10/10 kOm	SOT346,SC59	B-E-C
24	DTC114EUA	ROHM	Dnpn	V_{CB0} =50 B; I_C =100 mA; P_0 =200 mBT; h_{21} >30; f_T >250 MFu; R_1/R_2 =47/47 KOM	SOT323,SC70	B·E·C
24	MMBT3646	ON	npn	V _{CB0} =40 B; I _C =300 мА; P _D =625 мВт; h ₂₁ >15	SOT23,SOD23	B·E·C
24	PDTC114TE	PHIL	Dnpn	V _{C80} =50 B; I _C =100 mA; P ₀ =200 mBr; h ₂₁ >200; R ₁ 10 kOm	SOT416,SC75A	B·E·C
24	PDTC114TK	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 мA; P _D =200 мВт; h ₂₁ > 200; R ₁ 10 кОм	SOT346,SC59	B·E·C
24p	BF556A	PHIL	nFET	V _{DS} =30 B; I _{DSS} =7 mA; P _D =250 mBT; g _F >4.5 mc	SOT23,SOD23	S·D·G
24t	BF556A	PHIL	nFET	V _{DS} =30 B; I _{DSS} =7 mA; P _D =250 mBT; g _F >4.5 mc	SOT23,SOD23	S·D·G
24V	PZM24NB	PHIL	dz	V ₂ (I _{ZT} =5 mA)=22.9325.57 B; Z _{ZT} (I _{ZT} =5 mA)<30 Om	SOT346,SC59	A·n.c.·K
24W	BF556A	PHIL	nFET	V _{DS} =30 B; I _{DSS} =7 мА; Р _D =250 мВт; g _F >4.5 мс	SOT23,SOD23	S-D-G
24X	02CZ24	TOSH	dz	$V_2(I_{Z1}^-5 \text{ MA})^2$ 22.8025.60 B; $I_L(V_{R1}^-19 \text{ B}) < 0.5 \text{ M/A}$; $I_{Z2}^-(I_{Z1}^-0.5 \text{ MA}) < 200 \text{ DM}$	SOT346,SC59	A·n.c.·K
25	DTC124EE	ROHM	Dnpn	V_{C80} = 50 B; $I_{C(mog)}$ = 100 mA; P_D = 150 mBT; h_{21} > 56; f_T > 250 MFu; P_T/P_D = 22/22 kOm	SOT416,SC75A	B-E-C
25	DTC124EKA	ROHM	Dnpn	V _{CR0} =50 B; I _C =30 mA; P _D =200 mBT; h ₂₁ >56; f _T >250 MFu; R ₁ /R ₂ =22/22 kOm	SOT346,SC59	B·E·C
25	DTC124EUA	ROHM	Dnpn	V _{CB0} :50B; I _C :30 MA; P _D :200 MBT; h ₂₁ >56; f _T >250 MFц; R ₁ /R ₂ :22/22 KOM	SOT323,SC70	T-000T-000
25	MMBD1202	ON	di	V _B < 100 B; I _E < 200 мA; V _E (I _E =200 мA) < 1 B; C _n < 2 пФ; t _{EB} < 3 нс	SOT23 SOD23	





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
25	PDTA143XK	PHIL	Dpnp	V _{CB0} =50 B; I _C =100 mA; P _D =250 mBT; h ₂₁ > 50; 4.7 kOm/10 kOm	SOT346,SC59	B·E·C
250	KTY82-250	PHIL	rts	T _{AMB} =-55150°C; R ₂₅ =19002100 O _M	SOT23,SOD23	CONT1 · CONT2 · SUB
251	KTY82-251	PHIL	rts	T _{AMB} =-55150°C; R ₂₅ =19002000 O _M	SOT23,SOD23	CONT1 · CONT2 · SUB
252	KTY82-252	PHIL	rts	T _{AMB} =-55150°C; R ₂₅ =20002100 O _M	SOT23,SOD23	CONT1 · CONT2 · SUB
25p	BF556B	PHIL	nFET	V _{DS} =30B; I _{DSS} =13 мА; Р _D =250 мВт; g _F >4.5 мс	SOT23,SOD23	S·D·G
25t	BF556B	PHIL	nFET	V _{DS} =30B; I _{DSS} =13 mA; P _D =250 mBt; g _F >4.5 mc	SOT23,SOD23	S·D·G
25W	BF556B	PHIL	nFET	V _{DS} =30B; I _{DSS} =13 мА; Р _D =250 мВт; g _F >4.5 мс	SOT23,SOD23	S·D·G
26	DTC144EE	ROHM	Dnpn	V_{CB0} =50 B; $I_{G(mss)}$ =100; P_0 =150 MBT; h_{21} >68; f_T >250 MFu; R_1/R_2 =47/47 KOM	SOT416,SC75A	B-E-C
26	DTC144EKA	ROHM	Dnpn	$V_{CB0}\text{=}50B;I_{C}\text{=}30\text{mA};P_{D}\text{=}200\text{mBT};h_{21}\text{>}68;f_{T}\text{>}250\text{M}\Gamma\text{u};R_{1}/R_{2}\text{=}47/47\text{kOm}$	SOT346,SC59	B-E-C
26	DTC144EUA	ROHM	Dnpn	$V_{C80}\text{=}50B;I_{0}\text{=}30\text{mA};P_{0}\text{=}200\text{mBT};h_{21}\text{>}68;f_{T}\text{>}250\text{MFu};R_{1}/R_{2}\text{=}47/47\text{kOm}$	SOT323,SC70	B·E·C
26	MMBD1203	FAIR	di×2	$V_R \le 100 \text{ B}; I_F \le 200 \text{ mA}; V_R I_F = 200 \text{ mA}) \le 1 \text{ B}; C_D \le 2 \text{ n}\Phi; t_{RR} \le 3 \text{ Hc}$	SOT23,SOD23	A1 · K2 · K1,A2
26	PDTC143XK	PHIL	Dnpn	V _{CB0} =50 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ >50; 4.7 кОм/10 кОм	SOT346,SC59	B·E·C
26р	BF556C	PHIL	nFET	V _{DS} =30 B; I _{DSS} =18 mA; P _D =250 mBr; g _F >4.5 mc	SOT23,SOD23	200 0
26t	BF556C	PHIL	nFET	V _{DS} =30B; I _{DSS} =18 mA; P _D =250 mBr; g _F >4.5 mc	SOT23,SOD23	A6733 72
26W	BF556C	PHIL	nFET	V _{DS} =30B; I _{DSS} =18 mA; P _D =250 mBt; g _F >4.5 mc	SOT23,SOD23	S·D·G
27	MMBD1204	FAIR	di×2	$V_R \le 100 \text{ B}; I_F \le 200 \text{ mA}; V_F (I_F = 200 \text{ mA}) \le 1 \text{ B}; C_0 \le 2 \pi \Phi; t_{RR} \le 3 \text{ Hc}$	SOT23,SOD23	A1-A2-K1,K2
27A	MMBZ20VAL	ON	dz×2	V _Z (I _{ZT} =1 mA)=25.6528.35 B; V _E (I _E =10 mA) < 0.9 B	SOT23,SOD23	K1 · K2 · A1 ,A2
27V	PZM27NB	PHIL	dz	V _Z (I _{ZT} =2 mA)=25.128.9 B; Z _{ZT} (I _{ZT} =2 mA) < 40 Om	SOT346,SC59	A+n.c.+K
27X	02CZ27	TOSH	dz	V _Z (I _{ZT} =2 mA)=25.1028.90 B; I _E (V _R =21B)<0.5 mKA; Z _{ZT} (I _{ZT} =0.5 mA)<250 Om	SOT346,SC59	A+n.c.+K
28	MMBD1205	FAIR	di×2	V _R <100 B; I _F <200 mA; V _F (I _F =200 mA)<1 B; C _D <2πΦ; t _{RR} <3 Hc	SOT23,SOD23	K1 · K2 · A1,A2
28p	BF861A	PHIL	nFET	V _{DS} =25B; I _{DSS} =6.5 mA; P _D =250 mBT; g _F >12 mc	SOT23,SOD23	S·D·G
28t	BF861A	PHIL	nFET	V _{DS} =25B; I _{DSS} =6.5 мА; Р _D =250 мВт; g _F > 12 мс	SOT23,SOD23	S·D·G
28W	BF861A	PHIL	nFET	V _{DS} =25B; I _{DSS} =6.5 mA; P _D =250 mBT; g _F > 12 mc	SOT23,SOD23	S·D·G
29	DTC115EE	ROHM	Dnpn	V_{CB0} =50 B; $I_{C(mso)}$ =100 mA; P_0 =150 mB τ ; h_{21} >82; f_τ >250 M Γ_U ; P_1/P_0 =100/100 kOm	S0T416,SC75A	B-E-C
29	DTC115EKA	ROHM	Dnpn	V_{CB0} =50 B; I_C =20 MA; P_0 =200 MBT; h_{21} >82; f_T >250 MFu; R_1/R_2 =100/100 kOM	SOT346,SC59	B·E·C
29	DTC115EUA	ROHM	Dnpn	V_{CB0} -50 B; I_{c} -30 mA; P_{0} -200 mBT; h_{21} >82; f_{7} >250 MFu; R_{1}/R_{2} =100/100 kOm	S0T323,SC70	B·E·C
29	MMBD1401	FAIR	d	V _R <175 B; I _F <600 mA; V _F (I _F =200 mA) <1 B; I _R <0.1 mxA; C _D <2 πΦ	SOT23,SOD23	A·n.c.•K
29p	BF861B	PHIL	nFET	V _{DS} =25B; I _{DSS} =15mA; P _D =250 mBt; g _F >16mc	SOT23,SOD23	S·D·G
29t	BF861B	PHIL	nFET	V _{DS} =25B; I _{DSS} =15мA; P _D =250 мВт; g _F >16мс	SOT23,SOD23	S·D·G
29W	BF861B	PHIL	nFET	V _{DS} =25B; I _{DSS} =15мA; Р _D =250 мВт; g _F >16мс	SOT23,SOD23	S·D·G
2A	FMMT3906	ZETEX	pnp	V _{CB0} =40 B; I _C =200 мА; P _D =330 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	B·E·C
2A	KST3906	SAMS	pnp	V _{CB0} =40 B; I _C =200 мА; P _D =350 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	B·E·C
2A	MMBT3906	VISH	pnp	V _{CB0} =40 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	B·E·C
2A	MMBT3906LT1	MOT	pnp	V _{CB0} =40 B; I _C =200 мА; P _D =300 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	B·E·C
2A	MMBT3906WT1	MOT	pnp	V _{CB0} =40 B; I _C =200 мА; P _D =300 мВт; h ₂₁ =100300; f _T >250 МГц	SOT323,SC70	B·E·C
2A	TMPT3906	ALLEG	pnp	V _{CB0} =40 B; h ₂₁ =100300; V _{CE(sat)} <0.25 B; f _T >250 MΓι ₄	SOT23,SOD23	B·E·C
2A4	PZM2.4NB2A	PHIL	dz×2	V _z (I _{ZT} =5 мA)=2.32.6B; Z _{ZT} (I _{ZT} =5 мA)<100 Ом	SOT346,SC59	K1 · K2 · A1,A2
2A7	PZM2.7NB2A	PHIL	dz×2	V _Z (I _{ZT} =5 mA)=2.652.9B; Z _{ZT} (I _{ZT} =5 mA)<100 Om	SOT346,SC59	K1 · K2 · A1 ,A2
2AQ	2SD1304Q	PAN	npn	V _{CB0} =20 B; I _C =100 mA; P _D =200 mBT; h ₂₁ =160260	SOT23,SOD23	B·E·C
2AR	2SD1304R	PAN	npn	V _{CB0} =20B; I _C =100 mA; P _D =200 mBT; h ₂₁ =210340	SOT23,SOD23	B-E-C
2AS	2SD1304S	PAN	npn	V _{CB0} =20 B; I _C =100 mA; P _D =200 mBT; h ₂₁ =290460	SOT23,SOD23	B·E·C
2B	BC849B	IΠ	npn	V _{GB0} =30 B; I _G =100 мА; P _D =330 мВт; h ₂₁ =200450; f _T >300 МГц	SOT23,SOD23	B·E·C
2B	BC849B	CDIL	non	V _{CB0} =30 B; I _C =100 mA; P ₀ =330 mBT; h ₂₁ =200450; f ₁ >300 MFu	SOT23,SOD23	B-E-C
2B	BC849B	TOSH	npn	V _{CB0} =30 B; I _C =100 mA; P _D =150 mBT; h ₂₁ =200450; f _T =300 MFu,	SOT23,SOD23	
2B	BC849B	ZETEX	non	V _{CB0} =30 B; I _C =100 мА; P ₀ =330 мВт; h ₂₁ =200450; f ₁ >300 МГц	SOT23,SOD23	B·E·C
2B	FMMT2907	ZETEX	pnp	V _{CB0} =60 B; I _S =600 мA; P ₀ =330 мВт; h ₂₁ =100300; f _T >200 МГц	SOT23.SOD23	B+E+C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
2B	KST2907	SAMS	pnp	V _{G80} =60 B; I _C =600 MA; P _D =350 MBT; h ₂₁ >75; f _T >200 MFu	SOT23,SOD23	B·E·C
B	MMBT2907	VISH	pnp	V_{C80} = 40 B; I_C = 500 mA; P_D = 310 mBr; h_{21} = 100300; f_T > 200 MFu	SOT23,SOD23	B·E·C
2B	MMBT2907	MOT	pnp	V ₀₈₀ =40 B; I ₀ =500 мА; P ₀ =310 мВт; h ₂₁ =100300; f _T >200 МГц	SOT23,SOD23	B·E·C
2B	TMPT2907	ALLEG	pnp	V _{G80} =60 B; I _{G80} <20 HA; h ₂₁ =100300; V _{GF(sat)} <0.4 B; f _T >200 MFu,	SOT23,SOD23	B·E·C
2B-	BC849BW	PHIL	npn	V _{сво} =30 B; I _C =100 мA; P _D =200 мВт; h ₂₁ =200450; f _T >100 МГц	SOT323,SC70	1000000000
2BP	2SK374P	PAN	nFET	V _{BS} =55B; I _n =10 mA; P _n =200 mBr; Q _F >2.5 mCm; I _{DSS} =13 mA	SOT23,SOD23	S-D-G
2BP	2SK663P	PAN	nFET	V _{DS} =55 B; I _D =30 MA; P _D =150 MBt; Q _E >2.5 MCM; I _{DSS} =13 MA	SOT323,SC70	S·D·G
2Bo	BC849B	PHIL	non	V _{G80} =30 B; I _C =100 mA; P _D =250 mBt; h ₂₁ =200450; f _T >100 MFu	SOT23,SOD23	140.000
2BQ	2SK374Q	PAN	nFET	V _{BS} =55B; I _D =10 MA; P _D =200 MBT; Q _E >2.5 MCM; I _{DSS} =26.5 MA	SOT23,SOD23	
2BQ	2SK663Q	PAN	nFET	V _{DS} =55 B; I _D =30 MA; P _D =150 MB;; g _F >2.5 MCM; I _{DSS} =26.5 MA	SOT323.SC70	
2BR	2SK374R	PAN	nFET	V _{6S} =55B; I _D =10 MA; P _D =200 MBT; Q _E >2.5 MCM; I _{DSS} =512 MA	SOT23,SOD23	
2BR	2SK663R	PAN	nFET	V _{DS} = 55 B; I _D = 30 MA; P _D = 150 MBT; Q _F > 2.5 MCM; I _{DSS} = 512 MA	SOT323.SC70	
2BR	BC849BR	PHIL	npn	V _{C80} =30 B; I _C =100 мA; P _D =310 мВт; h ₂₁ =330; f _T >300 МГц	SOT23.SOD23	200000 300
2BS	2SK374S	PAN	nFET	V _{6S} : 55B; I ₀ : 10 MA; P ₀ : 310 MBT; Q _F > 2.5 MCM; I _{DSS} : 1020 MA	SOT23,30D23	N. C.
2Bs	BC849B	INF			SOT23,SOD23	700,000 -00
		INF	npn	V _{CB0} =30 B; I _C =100 mA; P _D =330 mBr; h ₂₁ =200450; f _T =250 MFu		
2Bs	BC849BT	-	npn	V _{CB0} =30 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =200450; f _T =250 MFu	SOT416,SC75A	
2Bs	BC849BW	INF	npn	V _{C80} =30 B; I _C =100 мА; P _D =250 мВт; h ₂₁ =200450; f _T =250 МГц	SOT323,SC70	
2Bt	BC849B	PHIL	npn	V _{C80} =30 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =200450; f _T >100 МГц	SOT23,SOD23	70070070
2Bt	BC849BW	PHIL	npn	V_{CB0} =30 B; I_C =100 xA; P_D =200 xBT; h_{21} =200450; f_T >100 MFu	SOT323,SC70	1150 11 130
2BZ	FMMT2907	ZETEX	pnp	V _{CBO} =60 B; I _C =600 мА; P _D =330 мВт; h ₂₁ =100300; f _T >200 МГц	SOT23,SOD23	32232 22
2C	BC849C	Ш	npn	V_{CB0} =30 B; I_C =100 mA; P_0 =330 mBt; h_{21} =420800; f_1 >300 M Γ_{LL}	SOT23,SOD23	
2C	BC849C	CDIL	npn	$V_{C80}=30 \text{ B}; I_C=100 \text{ mA}; P_0=330 \text{ mBT}; h_{21}=420800; f_T>300 \text{ MFL}$	SOT23,SOD23	
2C	BC849C	TOSH	npn	V _{CB0} =30 B; I _C =100 мA; P _D =150 мВт; h ₂₁ =420800; f _T =300 МГц	SOT23,SOD23	B·E·C
2C	BC849C	ZETEX	npn	V_{C80} =30 B; I_C =100 mA; P_D =330 mBT; h_{21} =420800; f_T >300 MFu	SOT23,SOD23	B·E·C
2C	BC849C	Ш	npn	V_{C80} =30 B; I_C =100 mA; P_D =330 mBr; h_{21} =420800; f_T >300 MFu	SOT23,SOD23	B-E-C
2C	TMPTA70	ALLEG	pnp	I _{CBO} < 100 нА; h ₂₁ =40 100; V _{CE(set)} <0.25 В; f ₇ >125МГц	SOT23,SOD23	B-E-C
2C-	BC849CW	PHIL	npn	V_{C80} =30 B; I_C =100 mA; P_D =200 mBt; h_{21} =420800; f_T >100 MFu	SOT323,SC70	B·E·C
2Cp	BC849C	PHIL	npn	V_{C80} =30 B; I_C =100 mA; P_D =250 mBr; h_{21} =420800; f_T >100 M Γ_{LL}	SOT23,SOD23	B·E·C
2CR	BC849CR	PHIL	npn	V _{CB0} =30 B; I _C =100 mA; P _D =310 mBr; h ₂₁ =600; f _T >300 MFu	SOT23,SOD23	E·B·C
2Cs	BC849C	INF	npn	V _{C80} =30 B; I _C =100 mA; P _D =330 mBt; h ₂₁ =420800; f _T =250 MFu,	SOT23,SOD23	B-E-C
2Cs	BC849CT	INF	npn	V _{сво} =30 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =420800; f _T =250 МГц	SOT416,SC75A	B·E·C
2Cs	BC849CW	INF	non	V _{CB0} =30 B; I _C =100 мA; P _D =250 мВт; h _{P1} =420800; f _T =250 МГц	SOT323,SC70	B·E·C
2Ct	BC849C	PHIL	npn	V ₀₈₀ =30 B; I ₀ =100 мA; P ₀ =250 мВт; h ₂₁ =420800; f _T >100 МГц	SOT23,SOD23	B·E·C
2Ct	BC849CW	PHIL	non	V _{G80} =30 B; I _C =100 mA; P _D =200 mBr; h ₂₁ =420800; f _T >100 MFu	SOT323.SC70	
2CZ	FMMTA70	ZETEX	qnq	V _{гап} =40 B; I _с =100 мА; Р _п =330 мВт; h _№ =40400; f _T >125 МГц	SOT23,SOD23	
2D	BC849	CDIL	non	V _{C80} =30 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =200800; f _T >100 MFu	SOT23,SOD23	
2D	BC849W	PHIL	ngn	V _{CR0} =30 B; I _C =100 MA; P _D =200 MBT; h _{P1} =200800; f _T >100 MFL	SOT323.SC70	SA PARKSON IN
2D	KST92	SAMS	pnp	V _{C80} =300 B; I _C =500 мА; Р _D =350 мВт; h ₂₁ >40; f _T >50 МГц	SOT23.SOD23	100/04/19/3
2D	MBTA92	TOSH		V _{CR0} =300 B; I _C =300 мА; Р _D =250 мВт; I _C =40; I _T =50 МГц	SOT23,SOD23	
2D 2D	MMBT4125	MOT	pnp	000		
	200000000000000000000000000000000000000		pnp	V _{C80} =30B; I _C =200 MA; P _D =350 MBt; h ₂₁ =50150	SOT23,SOD23	
2D	MMBTA92	VISH	pnp	V _{CB0} =300 B; I _C =500 MA; P _D =300 MBT; h ₂₁ =25; f _T >50 MFц	SOT23,SOD23	
2D	MMBTA92	MOT	pnp	V _{C80} =300 B; I _C =500 мА; P _D =300 мВт; h ₂₁ =25; f _T >50 МГц	SOT23,SOD23	
2Dp	BC849	PHIL	npn	V _{C80} =30 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =200800; f _T >100 МГц	SOT23,SOD23	
2Dt	BC849	PHIL	npn	V _{CB0} =30 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =200800; f _T >100 МГц	SOT23,SOD23	1,000-000-001
2E	FMMTA93	ZETEX	pnp	V _{GB0} =200 B; I _G =200 мА; P _D =330 мВт; h ₂₁ =30150; f _T >50 МГц	SOT23,SOD23	100,000
2E	KST93	SAMS	pnp	V _{CB0} =200 B; I _C =500 мА; P _D =350 мВт; h ₂₁ >40; f _T >50 МГц	SOT23,SOD23	155.555
2E	MMBTA93	MOT	pnp	V_{C80} =200 B; I_C =500 mA; P_D =300 mBT; h_{21} =25; f_T >50 MFu,	SOT23,SOD23	
2F	BC850B	Ш	npn	V_{C80} =50 B; I_C =100 mA; P_0 =250 mBT; h_{21} =200450; f_T >100 M Γ_{II}	SOT23,SOD23	B•E•C
2F	BC850B	CDIL	npn	V_{C80} =50B; I_C =100 mA; P_D =250 mBt; h_{21} =200450; f_T >100 M Γ_{II}	SOT23,SOD23	B·E·C
2F	FMMT2907A	ZETEX	pnp	V_{C80} =60 В; I_C =600 мА; P_D =330 мВт; h_{21} =100300; f_T >200 МГц	SOT23,SOD23	B-E-C
2F	KST2907A	SAMS	pnp	V_{CB0} =60 B; I_C =600 mA; P_D =350 mBr; h_{21} =100300; f_T >200 MFu	SOT23,SOD23	B-E-C
2F	MBT2907A	TOSH	pnp	V _{CB0} =60 B; I _C =600 MA; P _D =250 MBT; h ₂₁ >50; f _T =200 MFu,	SOT23,SOD23	B·E·C





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
2F	MMBT2907A	VISH	pnp	V _{CB0} =60 B; I _C =500 мА; P _D =310 мВт; h ₂₁ =75300; f _T <200 МГц	SOT23,SOD23	B·E·C
2F	MMBT2907ALT1	MOT	pnp	V _{CR0} =60 B; I _C =600 mA; P _D =300 mBT; h ₂₁ =100300; f _T >200 MFu	SOT23,SOD23	B·E·C
2F	MMBT2907AWT1	МОТ	pnp	V _{CB0} =60 B; I _C =600 мА; P ₀ =300 мВт; h ₂₁ =100300; f _T >200 МГц	SOT323,SC70	B·E·C
2F	TMPT2907A	ALLEG	pnp	V _{CB0} =60 B; I _{CB0} <10 HA; h ₂₁ =100300; V _{CBIsati} <0.4 B; f ₇ >200 MΓц	SOT23.SOD23	B-E-C
2F-	BC850BW	PHIL	non	V _{CB0} =50 B; I _C =100 MA; P ₀ =200 MBT; h ₂₁ =200450; f _T >100 MFu	SOT323,SC70	B·E·C
2Fp	BC850B	PHIL	non	V _{CB0} =50 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =200450; f _T >100 MFµ	SOT23,SOD23	B-E-C
2FR	2SB792AR	PAN	pnp	V _{CR0} =185 B; I _C =50 мА; P _D =200 мВт; h ₂₁ =130220; f _T =200 МГц	SOT23,SOD23	B-E-C
2FR	BC850BR	PHIL	non	V _{CR0} =45B; I _C =100 MA; P _D =310 MBT; h ₂₁ =330; f _T >300 MFu	SOT23,SOD23	E·B·C
2FS	2SB792AS	PAN	pnp	V _{CR0} =185B; I _C =50 MA; P _D =200 MBT; h ₂₁ =185330; f _T =200 MFu,	SOT23.SOD23	
2Fs	BC850B	INF	non	V _{CB0} =50 B; I _C =100 MA; P _D =330 MB; I _{D2} =200450; I _T =250 MFu	SOT23,SOD23	
2Fs	BC850BT	INF	non	Vcen=50 B; Ic = 100 mA; Pn=330 mBr; Ing = 200450; fr=250 MFu	S0T416,SC75A	
2Fs	BC850BW	INF	non	V _{CB0} *50B; I _C *100MA; P _D *250MBT; h ₂₁ *200450; f _T *250MFц	S0T323.SC70	
2Ft	BC850B	PHIL	non	V _{CB0} -50B; I _C =100мA; P _D =250мBт; h ₂₁ =200450; f _T >100МГц	SOT23.SOD23	532000070
2Ft	BC850BW	PHIL	non	V _{CB0} =50B; I _C =100 MA; P _D =200 MBT; h ₂₁ =200450; f _T >100 MFц	S0T323.SC70	000000000000000000000000000000000000000
2FZ	BC850B	ZETEX	non	V _{CR0} =50 B; I _C =100 MA; P _D =330 MBT; h ₂₁ =200450; f _T >300 MFц	SOT23,SOD23	
2G	BC850C	ITT	non	V _{CB0} -50B; I _C =100мA; P _D =350мBT; I _{CD} =220450; I _T >350мIII; V _{CB0} =50B; I _C =100мA; P _D =250мBT; I _{CD} =420800; f _T >100МГц	SOT23,SOD23	
2G	BC850C	CDIL	non	V _{CB0} -50B, I _C -100 мА; P _D -250 мВт; I ₁₂₁ -420600; I _T >100 МГц V _{CB0} -50B; I _C -100 мА; P _D -250 мВт; I ₁₂₁ -420800; I _T >100 МГц	SOT23,SOD23	
2G	BC850C	ITT	non	000	SOT23,SOD23	
			- special	V _{CB0} =50 B; I _C =100 мA; P _D =330 мВт; h ₂₁ =420800; f _T >300 МГц		
2G 2G	FMMTA56	ZETEX	pnp	V _{CB0} =80 B; I _C =500 MA; P _D =330 MBT; h ₂₁ >50; f _T >100 MFц	SOT23,SOD23	
	KST56	SAMS	pnp	V _{CB0} =80 B; I _C =500 MA; P _D =350 MBT; h ₂₁ >50; f _T >50 MFц	SOT23,SOD23	
2G	MMBTA56	VISH	pnp	V _{C80} =80 B; I _C =500 mA; P _D =350 mBT; h ₂₁ > 50; f _T < 50 MFц	SOT23,SOD23	
2G	MMBTA56	MOT	pnip	V_{CB0} =80 B; I_C =500 mA; P_D =350 mBT; h_{21} >50; f_T <100 MF $_U$	SOT23,SOD23	
2G	TMPTA56	ALLEG	pnp	V_{CB0} =80 B; I_{CB0} <100 HA; h_{21} >50; $V_{CE(sat)}$ <0.25 B; f_T >50 MFu	SOT23,SOD23	
2G-	BC850CW	PHIL	non	V _{CB0} =50 B; I _C = 100 мА; P _D =200 мВт; h ₂₁ =420800; f _T > 100 МГц	SOT323,SC70	
2Gp	BC850C	PHIL	non	V _{CB0} =50 B; I _C =100 мA; P ₀ =250 мВт; h ₂₁ =420800; f _T >100 МГц	SOT23,SOD23	
2GR	BC850CR	PHIL	non	V _{CB0} =45B; I _C =100 мA; P _D =310 мВт; h ₂₁ =600; f _T >300 МГц	SOT23,SOD23	70,700,000
2Gs	BC850C	INF	npn	V _{CB0} =50 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =420800; f ₁ =250 МГц	SOT23,SOD23	
2Gs	BC850CT	INF	npn	V _{C80} =50 B; I _C =100 мА; P ₀ =330 мВт; h ₂₁ =420800; f ₁ =250 МГц	SOT416,SC75A	
2Gt	BC850C	PHIL	npn	V _{CB0} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =420800; f _T >100 МГц	SOT23,SOD23	B.E.C
2Gt	BC850CW	PHIL	npn	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBT; h_{21} =420800; f_T >100 MFu	SOT323,SC70	B.E.C
2GT	SOA56	STM	pnp	V_{CB0} =80 B; I_C =500 mA; P_D =350 mBT; h_{21} >50; f_1 >50 MF μ	SOT23,SOD23	B.E.C
2H	BC850	CDIL	npn	V_{CB0} =50 B; I_C = 100 mA; P_D =250 mBT; h_{21} =200800; f_T > 100 M Γ_{LL}	S0T23,S0D23	B·E·C
2H	BC850W	PHIL	non	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ =200800; f _T >100 MFu,	S0T323,SC70	B.E.C
2H	FMMTA55	ZETEX	pnp	V _{CB0} =60 B; I _C =500 мА; P _D =330 мВт; h ₂₁ >50; f _T >100 МГц	SOT23,SOD23	B·E·C
2H	KST55	SAMS	pnp	V _{CB0} =60 B; I _C =500 mA; P _D =350 mBT; h ₂₁ >50; f _T >50 MFu	SOT23,SOD23	B·E·C
2H	MMBTA55	VISH	pnp	V _{CB0} =60 B; I _C =500 мА; P ₀ =225 мВт; h ₂₁ =50; f _T >50 МГц	SOT23,SOD23	B·E·C
2H	MMBTA55	MOT	prijo	$V_{CB0}=60 \text{ B}; I_C=500 \text{ mA}; P_D=225 \text{ mBT}; h_{21}=50; f_T>100 \text{ MFu}$	SOT23,SOD23	B·E·C
2H	TMPTA55	ALLEG	pnp	V _{CB0} =60 B; I _{CB0} < 100 нА; h ₂₁ > 50; V _{CE(sat)} < 0.25 B; f _T > 50 МГц	SOT23,SOD23	B·E·C
2Нр	BC850	PHIL	non	V _{CB0} =50 B; I _C =100 мА; P ₀ =250 мВт; h ₂₁ =200800; f ₁ >100 МГц	SOT23,SOD23	B·E·C
2HT	SOA55	STM	pnp	V _{CB0} =60 B; I _C =500 mA; P _D =625 mBT; h ₂₁ > 100; f _T >50 MFu	SOT23,SOD23	B·E·C
2J	MMBT3640LT1	МОТ	pnp	V _{CR0} =12B; I _C =80 MA; P _D =300 MBT; h ₂₁ =30120; f _T >500 MFu	SOT23,SOD23	
2K	FMMT4402	ZETEX	onp	V _{CR0} =40 B; I _C =600 мА; P _D =330 мВт; h ₂₁ =50150; f _T >150 МГц	SOT23, SOD23	
2K	MMBT8598LT1	МОТ	onp	V _{CB0} =60 B; I _C =500 mA; P _D =225 mBr; h ₂₁ >50; f _T >200 MFu	SOT23,SOD23	
2L	FMMT4403	ZETEX	pnp	V _{CB0} =40 B; I _C =600 мА; P _D =330 мВт; I _{D2} =100300; f _T >200 МГц	SOT23,SOD23	
2L	KST5401	SAMS	pnp	V _{CR0} =160B; I _C =500 mA; P _D =350 mBt; h ₂₁ =60240; f _T >150 MFц	SOT23,SOD23	550,000,000
2L	MMBT5401	VISH	pnp	V _{CBO} *160 B; I _C *200 мА; P _O *350 мВт; h ₂₁ *60240; f _T >100 МГц	SOT23,SOD23	
2L	MMBT5401	MOT	ono	V _{CB0} =150B; I _C =200 MA; P _D =350 MBr; h ₂₁ =40200; f _T >100MFц	SOT23.SOD23	14 55 55
2L	TMPT5401	ALLEG	onp	V _{CB0} =160 B; I _{CB0} < 50 HA; h ₂₁ =60240; V _{CB1sati} < 0.2 B; f ₁ > 100 MFu,	SOT23,SOD23	
2m	FMMT5087	ZETEX	pnp	V _{CB0} -50B; I _C =100MA; P _D =330MBT; h ₂₁ =250800; f _T >40MFц	SOT23,SOD23	
2N	MMBT404ALT1	MOT	prip	V _{CB0} =40 B; I _C =150 mA; P _D =330 mB1; h ₂₁ =230400	SOT23,SOD23	70000000
2NO	ZXT11N20DF	ZETEX			SOT23,SOD23	
LIVU	2SD1478Q	PAN	npn dnpn	$V_{C80}^{-4}0B; I_{c}^{-2}.5A; P_{D}^{-6}25 MBT; h_{21}^{-3}.300900; f_{T}^{-1}.160 MFU,$ $V_{C80}^{-3}0B; I_{c}^{-5}.500 MA; P_{D}^{-2}.200 MBT; h_{21}^{-2}.400010000$	SOT346,SC59	1001000000

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
2NR	2SD1478R	PAN	dnpn	V _{C80} =30 B; I _C =500 мA; P _D =200 мВт; h ₂₁ =800020000	SOT346,SC59	B-E-C
20Q	2SD1478AQ	PAN	dnpn	V _{G80} =60 B; I _C =500 мA; P _D =200 мВт; h ₂₁ =400010000	SOT346,SC59	B-E-C
20R	2SD1478AR	PAN	dnpn	V _{C80} =60 B; I _C =500 мA; P _D =200 мВт; h ₂₁ =800020000	SOT346,SC59	B-E-C
2P	FMMT2222R	ZETEX	npn	V_{C80} =60 B; I_C =600 mA; P_D =330 mBT; h_{21} =120360; f_T >250 MFu	SOT23,SOD23	B-E-C
2P	KST5086	SAMS	pnp	V_{C80} =50 B; I_C =50 mA; P_0 =350 mBT; h_{21} =150500; f_T >40 M Γ_{II}	SOT23,SOD23	B·E·C
2P	MMBT5086	MOT	ono	V_{C80} =50 B; I_C =50 mA; P_D =225 mBT; h_{21} =150600; f_T >40 MF $_U$	SOT23,SOD23	B-E-C
2P	TMPT5086	ALLEG	pnp	V _{G80} =50 B; I _{G80} <50 нА; h ₂₁ =150500; V _{GF(sat)} <0.3 B; f _T >40 МГц	SOT23,SOD23	B-E-C
2Q	FMMT5209	ZETEX	npn	V _{GR0} =50 B; I _G =50 mA; P _D =330 mBT; h ₂₁ =100300; f _T >30 MFц	SOT23,SOD23	B-E-C
2Q	KST5087	SAMS	pnp	V _{G80} =50 B; I _G =50 mA; P _D =350 mBT; h ₂₁ =250800; f _T >40 MFu	SOT23,SOD23	B·E·C
2Q	MMBT5087	MOT	ono	V _{G80} =50 B; I _G =50 mA; P _D =225 mBT; h ₂₁ =250900; f _T >40 MFu	SOT23,SOD23	B-E-C
2Q	TMPT5087	ALLEG	onp	V _{C80} =50B; I _{C80} <50 HA; h ₂₁ =250800; V _{CE(set)} <0.3B; f _T >40 MFu	SOT23,SOD23	B-E-C
2R	FMMT5210	ZETEX	npn	V_{CB0} =50 B; I_C =50 mA; P_D =330 mBT; h_{21} =200600; f_T >30 M Γ_{IJ}	SOT23,SOD23	1000000000
2R	HSMS-8102	HP	shd×2	V _{BB} >4B; V _E (I _E =1 мA)<0.35B; C _D <0.26 πΦ; R _D =14 Oм	SOT23,SOD23	100,000,000
2T	HT2	ZETEX	npn	V _{CR0} =90 B; I _C =100 MA; P _D =330 MBr; h ₂₁ >25	SOT23,SOD23	
2T	KST4403	SAMS	ono	V _{CR0} =60 B; I _C =600 MA; P _D =350 MBT; h ₂₁ =100300; f _T > 200 MFц	SOT23,SOD23	100
2T	MMBT4403	VISH	pnp	V _{CR0} =40 B; I _C =800 mA; P _D =200 mBr; h ₂₁ =100300; f _T >200 mFц	SOT23,SOD23	
2T	MMBT4403LT1	MOT	ono	V _{CR0} =40 B; I _C =600 mA; P _D =300 mBr; h ₂₁ =100300; f _T > 200 MFц	SOT23,SOD23	
2T	SO4403	STM	pub	V _{C80} =40 B; I _C =600 MA; P _D =350 MB; h ₂₁ =100300; f _T >200 MF _U	SOT23,SOD23	
2T	TMPT4403	ALLEG	ono	V _{C80} =40 B; h ₂₁ =100300; V _{CE1sat} < 0.4 B; f _T >200 MFц	SOT23,SOD23	1007003447964
2U	KST63	SAMS	prip	V _{CR0} =40 B, n ₂₁ =100300, v _{CE[sat]} < 0.4-b, n ₇ >200 м/п V _{CR0} =30 B; I _C =500 мА; P _D =350 мВт; h ₂₁ >5000; f ₇ >125 МГц	SOT23,30D23	
2U	MMBTA63LT1	MOT	dana	V _{C80} =30B; I _C =500 мA; P ₀ =300 мBr; h ₂₁ >5000; f ₁ >125 МГц	SOT23,SOD23	130000 20
2V	KST64	SAMS	1.1			
2V 2V	MMBTA64LT1	MOT	pnp	V _{C80} =30 B; I _C =500 xA; P _D =350 xBr; h ₂₁ >10000; f _T >125 MFu	SOT23,SOD23 SOT23,SOD23	
_	A CONTRACTOR OF THE PARTY OF TH	PHIL	dpnp	V _{CBO} =30 B; I _C =500 мA; P _D =300 мBт; h ₂₁ >10000; f _T >125 МГц		
2V4	PZM2.4NB		dz	V _Z (I _{ZT} =5 MA) = 2.32.6 B; Z _{Z1} (I _{ZT} =5 MA) < 100 OM	SOT346,SC59	100000000000000000000000000000000000000
2V7	PZM2.7NB	PHIL	dz	V _Z (I _{ZT} =5 MA)=2.52.9 B; Z _{ZT} (I _{ZT} =5 MA)<100 OM	SOT346,SC59	100000000000000000000000000000000000000
2W	2SC3704	PAN	npn	V _{CBO} =15B; I _C =80 mA; P _D =200 mBr; h ₂₁ =50300; f _T =6 fTu	SOT23,SOD23	
2W	2SC3937	PAN	npn	V _{CB0} =15B; I _C =80 MA; P _D =150 MBT; h ₂₁ =50300; f _T =6 TT _L	SOT323,SC70	
2W	FMMT3905	ZETEX	pnp	V _{CB0} =40 B; I _C =200 мA; P _D =330 мBr; h ₂₁ =50150; f ₁ >200 MΓ _Ц	SOT23,SOD23	
2W	MMBT8599LT1	MOT	pnp	V _{C80} =80 B; I _C =500 мA; P _D =300 мВт; h ₂₁ =100300; f _T >150 МГц	SOT23,SOD23	
2W	TMPT4402	ALLEG	pnp	V_{CB0} =40 B; h_{21} =50150; $V_{CE(sat)}$ <0.4 B; f_T >150 MFu	SOT23,SOD23	1000000000
2X	2SC3707	PAN	npn	V _{CB0} =10B; I _C =10мA; P _D =50мBт; h ₂₁ =50150; f _T =4ГГц	SOT23,SOD23	
2X	KST4401	SAMS	npn	V _{G80} =60 B; I _C =600 мA; P _D =350 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	1.000.70.002
2X	MMBT4401	VISH	npn	V _{CBO} =50 B; I _C =800 мA; P _D =200 мВт; h ₂₁ =100300; f _T >200 МГц	SOT23,SOD23	100
2X	MMBT4401LT1	MOT	npn	V _{GB0} =60 B; I _C =600 мA; P _D =300 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	
2X	SO4401	STM	npn	V _{G80} =60 В; I _C =600 мА; Р _D =350 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	
2X	TMPT4401	ALLEG	npn	V_{CB0} =60 B; I_{CB0} <100 HA; h_{21} =100300; $V_{CE[sat]}$ <0.4 B; f_{7} >250 MF $_{LL}$	SOT23,SOD23	SATISFACE OF STREET
2YQ	2SC3757Q	PAN	npn	V _{CBO} =40 B; I _C =300 мA; P _D =200 мВт; h ₂₁ =60120; f _T =450 МГц	SOT23,SOD23	10000111031
2YQ	2SC3938Q	PAN	npn	V _{CB0} =40 B; I _C =300 мA; P ₀ =150 мВт; h ₂₁ =60120; f _T =450 МГц	SOT323,SC70	1200000000
2YQ	2SC4691Q	PAN	npn	V _{C80} =40 B; I _C =100 мА; P ₀ =125 мВт; h ₂₁ =60120; f _T =450 МГц	SOT416,SC75A	B-E-C
2YR	2SC3757R	PAN	npn	V _{C80} =40 B; I _C =300 мA; P _D =200 мВт; h ₂₁ =90200; f _T =450 МГц	SOT23,SOD23	B.E.C
2YR	2SC3938R	PAN	npn	V_{CB0} =40 B; I_C =300 mA; P_D =150 mBt; h_{21} =90200; f_T =450 M Γ_{II}	SOT323,SC70	B-E-C
2YR	2SC4691R	PAN	npn	V_{C80} =40 B; I_C = 100 mA; P_D = 125 mBr; h_{21} =90200; f_T =450 MFu	SOT416,SC75A	B-E-C
2Z	BAS7004	ZETEX	shd×2	$V_R < 70B$; $V_E (I_F = 1 \text{ mA}) < 0.41B$; $I_R < 0.2 \text{ mKA}$; $C_D < 2.0 \text{ m}$	SOT23,SOD23	A1 · K2 · K1,A2
2Z	MMBT6520	MOT	pnp	V_{CB0} =350 B; I_C =500 mA; P_D =300 mBr; h_{E1} =20200; f_T >40 MFu	SOT23,SOD23	B-E-C
2Z5	BAS7005	ZETEX	shd×2	$V_R < 70B$; $V_P (I_P = 1 \text{ mA}) < 0.41B$; $I_R < 0.2 \text{ m/KA}$; $C_D < 2.0 \text{ m}$	SOT23,SOD23	A1+A2+K1,K2
2Z5	BAS70-05	ZETEX	shd×2	$V_R < 70B$; $I_F < 70 \text{ mA}$; $V_F (I_F = 1 \text{ mA}) < 410 \text{ mB}$; $C_D < 2 \text{ m}$	SOT23,SOD23	A1+A2+K1,K2
3.0X	02CZ3.0	TOSH	dz	$V_2(I_{ZT}=5 \text{ mA})=2.803.20 \text{ B; } I_1(V_R=1.0 \text{ B}) \le 50 \text{ m/sA; } Z_{ZT}(I_{ZT}=0.5 \text{ mA}) \le 1000 \text{ Om}$	SOT346,SC59	A·n.c.·K
3.3X	02CZ3.3	TOSH	dz	$V_Z(I_{ZT}=5 \text{ mA})=3.103.50 \text{ B; } I_X(V_R=1.0 \text{ B}) < 20 \text{ m/sA; } Z_{ZT}(I_{ZT}=0.5 \text{ mA}) < 1000 \text{ Om}$	SOT346,SC59	
3.6X	02CZ3.6	TOSH	dz	$V_2(I_{ZT}=5 \text{ mA})=3.403.80 \text{ B}; I_1(V_B=1.0 \text{ B})<10 \text{ m/A}; Z_{ZT}(I_{ZT}=0.5 \text{ mA})<1000 \text{ Om}$	SOT346,SC59	A·n.c.·K
3.9X	02CZ3.9	TOSH	dz	$V_2(I_{ZT}=5 \text{ mA})=3.704.10 \text{ B; } I_1(V_R=1.0 \text{ B})<10 \text{ m/A; } Z_{ZT}(I_{ZT}=0.5 \text{ mA})<1000 \text{ Om}$	SOT346,SC59	
301	FDV301N	FAIR		V _{DS} = 25 B; I _D = 220 MA; P _D = 350 MBT; R _{DS(DD)} = 5 OM	SOT23.SOD23	NEWS CONTRACTOR
302	FDV302P	FAIR		V _{DS} = -25 B; I _D = 120 mA; P _D = 350 mBr; R _{DS(on)} = 13 Om	SOT23,SOD23	- T T





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
303	FDV303N	FAIR	DnMOS	V _{DS} : 25B; I _D : 680 mA; P _D : 350 mBt; R _{DS(on)} : 0.45 Om	SOT23,SOD23	G·S·D
304	FDV304P	FAIR		V _{DS} =-25B; I _D =460 мА; P _D =350 мВт; R _{DS(DE)} =1.1 Ом	SOT23,SOD23	G·S·D
305	AT30533	HP	npn	V _{CB0} =11 B; I _C =8 мA; P _D =100 мВт; h ₂₁ =70300; f ₇ =10 ГГц	SOT23,SOD23	B·E·C
30p	BF861C	PHIL	nFET	V _{DS} =25B; I _{DSS} =25 MA; P _D =250 MBT; g _E >20 MC	SOT23,SOD23	S·D·G
30t	BF861C	PHIL	nFET	V _{DS} =25B; I _{DSS} =25MA; P _D =250 MBT; g _F >20 MC	SOT23,SOD23	S·D·G
30V	PZM30NB	PHIL	dz	V _A (I ₇₁ =2 mA)=28.032.0 B; Z ₂₁ (I ₇₁ =2 mA) < 40 Om	SOT346,SC59	A·n.c.·K
30W	BF861C	PHIL	nFET	V _{DS} =25B; I _{DSS} =25 MA; P _D =250 MBT; g _E >20 MC	SOT23,SOD23	S·D·G
30X	02CZ30	TOSH	dz	$V_X(I_{ZT}=2 \text{ MA})=28.0032.00 \text{ B}, I_L(V_R=23 \text{ B})<0.5 \text{ M/s}; \\ Z_{ZT}(I_{ZT}=0.5 \text{ M/s})<250 \text{ OM}$	SOT346,SC59	A+n.c.+K
31	MMBD1402	ON	d	$V_R \le 175 B$; $I_F \le 600 \text{ mA}$; $V_P (I_F = 200 \text{ mA}) \le 1 B$; $I_R \le 0.1 \text{ m/A}$; $C_D \le 2 \text{ m}\Phi$	SOT23,SOD23	n.c.+A+K
310	AT31033	HP	npn	V _{CB0} =11 B; I _C =16 мA; P _D =150 мВт; h ₂₁ =70300; f _T =10 ГГц	SOT23,SOD23	B·E·C
31p	BFR505	PHIL	npn	V _{CB0} =20 B; I _C =18 mA; P _D =150 mBT; h ₂₁ =60250; f _T =9 FFu	SOT23,SOD23	B·E·C
31t	BFR505	PHIL	npn	V _{CBO} =20 B; I _C =18 мA; P _D =150 мВт; h ₂₁ =60250; f _T =9 ГГц	SOT23,SOD23	B·E·C
31W	BFR505	PHIL	npn	V _{CB0} =20 B; I _C =18 мА; Р ₀ =150 мВт; h ₂₁ =60250; f ₇ =9 ГГц	SOT23,SOD23	B·E·C
32	MMBD1403	FAIR	d×2	$V_R < 175 B$; $I_F < 600 \text{ mA}$; $V_F (I_F = 200 \text{ mA}) < 1 B$; $I_R < 0.1 \text{ m/sA}$; $C_0 < 2 \text{ m}\Phi$	SOT23,SOD23	A1 · K2 · K1,A2
32	MMBD1403	ON	d×2	$V_R \le 175 B$; $I_F \le 600 \text{ MA}$; $V_F (I_F = 200 \text{ MA}) \le 1 B$; $I_R \le 0.1 \text{ M/A}$; $C_0 \le 2 \text{ m}$	SOT23,SOD23	A1 · K2 · K1,A2
320	AT32033	HP	npn	$V_{CB0}=11B$; $I_{C}=32$ mA; $P_{D}=200$ mBT; $h_{21}=70300$; $f_{T}=10$ TTu	SOT23,SOD23	B·E·C
32p	BFR520	PHIL	npn	V _{CBO} =20 B; I _C =70 мА; P _D =300 мВт; h ₂₁ =60250; f _T =9 ГГц	SOT23,SOD23	B·E·C
32t	BFR520	PHIL	npn	V _{CB0} =20 B; I _C =70 мА; P _D =300 мВт; h ₂₁ =60250; f _T =9 ГГц	SOT23,SOD23	B·E·C
32W	BFR520	PHIL	npn	V _{CB0} =20 B; I _C =70 мА; P _D =300 мВт; h ₂₁ =60250; f _T =9 ГГц	SOT23,SOD23	B·E·C
33	DTA143XE	ROHM	Dpnip	V_{CB0} -50B; I_C =100mA; P_0 =150mB τ ; h_{21} >30; f_1 >250 M Γ μ ; R_1/R_2 =4.7/10 κ Om	S0T416,SC75A	B·E·C
33	DTA143XKA	ROHM	Dpnip	V_{CB0} =50 B, I_C =100 mA; P_D =200 mBt; h_{21} >30; f_T >250 MFu; R_1/R_2 =4.7/10 kOm	SOT346,SC59	B-E-C
33	DTA143XUA	ROHM	Dpnp	V_{CB0} +50B; I_{C} =100mA; P_{D} =200mB τ ; h_{21} >30; f_{T} >250 M Γ u; R_{1}/R_{2} =4.7/10kOm	S0T323,SC70	B-E-C
33	MMBD1404	FAIR	d×2	$V_R < 175 B$; $I_F < 600 \text{ mA}$; $V_F (I_F = 200 \text{ mA}) < 1 B$; $I_R < 0.1 \text{ m/sA}$; $C_D < 2 \text{ m}\Phi$	SOT23,SOD23	A1-A2-K1,K2
33	MMBD1404	ON	d×2	$V_R \le 175 \text{ B}; I_F \le 600 \text{ mÅ}; V_F (I_F = 200 \text{ mÅ}) \le 1 \text{ B}; I_R \le 0.1 \text{ m/sÅ}; C_0 \le 2 \text{ m}$	SOT23,SOD23	A1+A2+K1,K2
33	PDTC114YE	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 мА; P ₀ =200 мВт; h ₂₁ >100; 10 кОм/47 кОм	SOT416,SC75A	B·E·C
331	NDS331N	FAIR	nMOS	V _{DS} =20B; I _D =1.3 A; P _D =500 мBт; R _{DS(on)} <0.40 м	SOT23,SOD23	G·S·D
332	NDS332P	FAIR	pMOS	V_{DS} = 20 B; I_D = 1 A; P_D =500 mBT; $P_{DS(on)}$ < 0.74 Om	SOT23,SOD23	G·S·D
335	NDS335N	FAIR	nMOS	V _{DS} =20B; I _D =1.7 A; P _D =500 мВт; R _{DS(on)} < 0.25 Ом	SOT23,SOD23	
336	NDS336P	FAIR	pMOS	V _{DS} =20B; I _D =1.2 A; P _D =500 mBt; R _{DS(on)} <0.49 0 m	SOT23,SOD23	
337	NDS337N	FAIR	nMOS	V _{DS} =20B; I _D =2.5 A; P _D =500 мBт	SOT23,SOD23	
338	NDS338P	FAIR	pMOS	V _{DS} =20B; I _D =1.6A; P _D =500 мBт	SOT23,SOD23	G·S·D
33A	MMBZ33VAL	ON	dz×2	V _Z (I _{ZT} =1 MA)=31.3534.65 B; V _E (I _E =10 MA) < 0.9 B	SOT23,SOD23	K1 · K2 · A1,A2
33p	BFR540	PHIL	npn	V _{CB0} =20 B; I _C = 120 мА; P _D =500 мВт; h ₂₁ = 100250; f _T =9 ГГц	SOT23,SOD23	-
33t	BFR540	PHIL	npn	V _{CB0} =20 B; I _C = 120 мА; P ₀ =500 мВт; h ₂₁ =100250; f _T =9 ГГц	SOT23,SOD23	T (457 - 550
33V	PZM33NB	PHIL	dz	$V_Z(I_{ZT}=2 \text{ mA})=31.035.0 \text{ B}; Z_{ZT}(I_{ZT}=2 \text{ mA}) < 40 \text{ Om}$	SOT346,SC59	A·n.c.·K
33W	BFR540	PHIL	npn	V _{CB0} =20 B; I _C = 120 мA; P _D =500 мВт; h ₂₁ = 100250; f _T =9 ГГц	SOT23,SOD23	
33X	02CZ33	TOSH	dz	$V_{\mathcal{L}} _{Z_{T}}=2$ mA)=31.0035.00 B; $I_{L}(V_{R}^{-}.25B)<0.5$ mkA; $Z_{Z_{L}}(V_{L}^{-}=0.5$ mA)<250 0 m	SOT346,SC59	
34	MMBD1405	FAIR	d×2	$V_R \le 175 \text{ B}; I_F \le 600 \text{ mA}; V_F (I_F = 200 \text{ mA}) \le 1 \text{ B}; I_R \le 0.1 \text{ msA}; C_D \le 2 \text{ n}\Phi$	SOT23,SOD23	
34	MMBD1405	ON	d×2	$V_R \le 175 \text{ B}; I_F \le 600 \text{ mA}; V_F (I_F = 200 \text{ mA}) \le 1 \text{ B}; I_R \le 0.1 \text{ m/A}; C_D \le 2 \text{ m}$	SOT23,SOD23	200 00000000000000000000000000000000000
34	PDTC143XE	PHIL	Dnpn	V _{CBO} =50 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ > 50; 4.7 кОм/10 кОм	SOT416,SC75A	
340	FDV340P	FAIR	DpMO S	V _{DS} =-20B; I _D =70 MA	SOT23,SOD23	G·S·D
35	DTA124XE	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =150 mBt; h_{21} >68; f_T >250 M Γ u; R_1/R_2 =22/47 кОм	SOT416,SC75A	B·E·C
35	DTA124XKA	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBt; h_{21} >68; f_T >250 MF I_L ; R_1/R_2 =22/47 кОм	SOT346,SC59	B·E·C
35	DTA124XUA	ROHM	Dpnp	V_{CB0} =50B; I_C =100mA; P_D =200mBT; h_{21} >68; f_T >250MFu; R_1/R_2 =22/47 KOM	SOT323,SC70	B·E·C
35	PDTA143XE	PHIL	Dpnp	V _{CB0} =50 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ >50; 4.7 кОм/10 кОм	S0T416,SC75A	B-E-C
351	NDS351N	FAIR	nMOS	V _{DS} =30B; I _D =1.1A; P _D =500 мВт	SOT23,SOD23	G·S·D
352	NDS352P	FAIR	pMOS	V _{DS} =20B; I _D =0.5 A; P _D =500 MBT	SOT23,SOD23	25000001000

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
355	NDS355N	FAIR	nMOS	V _{DS} =30 B; I _D =1.6A; P _D =500 мBт	SOT23,SOD23	G·S·D
356	NDS356P	FAIR	pMOS	V _{DS} =20 B; I _D =1.1A; P _D =500 MBT	SOT23,SOD23	G·S·D
357	NDS357N	FAIR	nMOS	V _{DS} =30 B; I _D =2.5A; P _D =500 MBT	SOT23,SOD23	G·S·D
358	NDS358P	FAIR		V _{DS} =30 B; I _D =1.6A; P _D =500 mBT	SOT23,SOD23	G·S·D
36	PDTA114YE	PHIL	Dpnp	V _{G80} =50 B; I _G =100 мА; P _D =200 мВт; h ₂₁ >100; 10 кОм/47 кОм	SOT416,SC75A	B·E·C
36	PDTC124EEF	PHIL	Dnpn	V _{C80} =50 B; I _C =100 mA; P _D =250 mBT; h ₂₁ >60; 22 kOm/22 kOm	SOT490,SC89	B·E·C
360	FDN360P	FAIR	DpMOS	V _{DS} =-30 B; I _D =2 A; P _D =500 MBT; R _{DS(D1)} =0.08 OM	SOT23,SOD23	G·S·D
36V	PZM36NB	PHIL	dz	V _Z (I _{ZT} = 2 mA) = 34.0 38.0 B; Z _{ZT} (I _{ZT} = 2 mA) < 60 Om	SOT346,SC59	A·n.c.·K
36X	02CZ36	TOSH	dz	$V_2(I_{ZT} = 2 \text{ MA}) = 34.0038.00 \text{ B}; I_k(V_{H} = 27 \text{ B}) < 0.5 \text{ MrA}; $ $Z_{ZT}(I_{ZT} = 0.5 \text{ MA}) < 250 \text{ Om}$	SOT346,SC59	A·n.c.·K
37	PDTA114YEF	PHIL	Dpnp	V _{CB0} =50 B; I _C =100 мА; P _D =200 мВт; h ₂₁ >100; 10 кОм/47 кОм	SOT490,SC89	B·E·C
37	PDTA143ZE	PHIL	Dpnp	V _{CB0} =50 B; I _C =100 mA; P _D =250 mBt; h ₂₁ >100; 4.7 кOm/47 кOm	SOT416,SC75A	B-E-C
38	PDTC143ZE	PHIL	Dnpn	V_{C80} =50 B; I_C =100 mA; P_D =250 mBt; h_{21} >100; 4.7 kOm/47 kOm	SOT416,SC75A	B·E·C
38p	PMBFJ108	PHIL	nFET	V _{DS} =25 B; I _{DSS} >80 mA; P _D =250 mBT; R _{DS(on)} <8 Om	SOT23,SOD23	D·S·G
38t	PMBFJ108	PHIL	nFET	V _{DS} =25 B; I _{DSS} >80 mA; P _D =250 mBT; R _{DS(ort)} <8 0 m	SOT23,SOD23	D·S·G
38W	PMBFJ108	PHIL	nFET	V _{DS} =25 B; I _{DSS} >80 mA; P _D =250 mBT; R _{DSfort} <8 Om	SOT23,SOD23	D·S·G
39p	PMBFJ109	PHIL	nFET	V _{DS} =25 B; I _{DSS} >40 mA; P _D =250 mBT; R _{DS(ot)} <12 Om	SOT23,SOD23	D·S·G
39t	PMBFJ109	PHIL	nFET	V _{DS} =25 B; I _{DSS} >40 mA; P _D =250 mBt; R _{DSignt} <12 Om	SOT23,SOD23	D·S·G
39V	PZM39NB	PHIL	dz	V _Z (I _{ZT} =2 MA)=37.041.0 B; Z _{ZT} (I _{ZT} =2 MA) < 75 Om	SOT346,SC59	A·n.c.·K
39W	PMBFJ109	PHIL	nFET	V _{DS} =25 B; I _{DSS} >40 mA; P _D =250 mBT; R _{DSion} < 12 Om	SOT23,SOD23	D·S·G
39X	02CZ39	TOSH	dz	V _Z (I _{ZT} =2 mA)=37.0041.00B; I _L (V _R =30B)<0.5mkA; Z _{ZT} (I _{ZT} =0.5 mA)<250 Om	SOT346,SC59	A·n.c.·K
3A	BC856A	CDIL	pnp	V_{G80} =80 B; I_C =100 mA; P_0 =310 mBr; h_{21} =110220; f_T >150 MFu	SOT23,SOD23	B·E·C
3A	BC856A	TOSH	pnp	V _{G80} =80 B; I _C =100 мA; P _D =150 мВт; h ₂₁ =125250; f _T =300 МГц	SOT23,SOD23	B-E-C
3A	BC856A	VISH	pnp	V _{G80} =80 B; I _C =100 мА; P _D =310 мВт; h ₂₁ =110220; f _T >150 МГц	SOT23,SOD23	B·E·C
3A	BC856A	ZETEX	pnp	V _{G80} = 80 В; I _C = 100 мА; P _D = 330 мВт; h ₂₁ = 125250; f _T > 150 МГц	SOT23,SOD23	B·E·C
3A	BC856A	DIODS	pnp	V _{GBO} =80 B; I _C =100 мA; P _D =300 мВт; h ₂₁ =125250; f _T >100 МГц	SOT23,SOD23	B·E·C
3A	BC856A	ITT	pnp	V _{GBO} =80 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =125250; f _T >150 МГц	SOT23,SOD23	B·E·C
3A	BC856AF	PHIL	pnp	V _{G80} = 80 B; I _G = 100 мА; P _D = 250 мВт; h ₂₁ = 125250; f _T > 100 МГц	SOT490,SC89	B·E·C
3A	BC856ALT1	MOT	pnp	V_{CB0} =80 B; I_C =100 mA; P_0 =300 mBr; h_{21} =125250; f_T >100 MFu,	SOT23,SOD23	B·E·C
3A	BC856AT	PHIL	pnp	V_{GB0} =80 B; I_C =100 MA; P_0 =150 MBr; h_{21} =125250; f_T >100 MFu	SOT416,SC75A	B·E·C
3A	KST24	SAMS	npn	V_{C80} =40 B; I_C =100 mA; P_D =350 mBr; h_{21} >30; f_T >620 MFu,	SOT23,SOD23	B·E·C
3A	MMBTH24	MOT	npn	V _{C80} =40 B; I _C =50 мA; P ₀ =300 мВт; h ₂₁ >30; f _T >400 МГц	SOT23,SOD23	B·E·C
3A-	BC856AW	PHIL	ono	V ₀₈₀ =80 B; I ₀ =100 mA; P ₀ =200 mBr; h ₂₁ =125250; f _T >100 MF _U	SOT323,SC70	
3A0	PZM3.0NB2A	PHIL	dz×2	V ₂ (I ₂₇ =5 mA)=2.953.2 B; Z ₂₇ (I ₂₇ =5 mA) < 95 Om	SOT346,SC59	
3A3	PZM3.3NB2A	PHIL	dz×2	V ₂ (I ₂₇ =5 mÅ)=3.253.5 B; Z ₂₇ (I ₂₇ =5 mÅ) < 95 Om	SOT346,SC59	K1-K2-A1.A2
3A6	PZM3.6NB2A	PHIL	dz×2	V ₂ (I ₂₇ =5 mA)=3.553.8 B; Z ₂₇ (I ₂₇ =5 mA) < 90 Om	SOT346,SC59	K1-K2-A1.A2
3A9	PZM3.9NB2A	PHIL	dz×2	V ₂ (I _{ZT} =5 mA)=3.874.1 B; Z _{ZT} (I _{ZT} =5 mA) < 90 Om	SOT346,SC59	
ЗАр	BC856A	PHIL	pnp	V _{CB0} =80 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =125250; f _T >100 MFц	SOT23,SOD23	
3AR	BC856AR	PHIL	pnp	V _{CB0} =65 B; I _C =100 мA; P _D =200 мBτ; h ₂₁ =125; f _T >150 MΓц	SOT23,SOD23	
3As	BC856A	INF	pnp	V ₀₈₀ =80 B; I ₀ =100 mA; P ₀ =330 mBr; h ₂₁ =125250; f ₁ =250 MFц	SOT23,SOD23	100000000000000000000000000000000000000
3As	BC856AT	INF	pnp	V ₀₈₀ =80 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =125250; f _T =250 MFц	SOT416,SC75A	B·E·C
3As	BC856AW	INF	ono	V _{CB0} =80 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =125250; f _T =250 МГц	SOT323,SC70	
3At	BC856A	PHIL	pnp	V _{CR0} =80 B; I _C =100 мA; P _D =250 мBτ; h ₂₁ =125250; f _T >100 MΓц	SOT23,SOD23	
3At	BC856AW	PHIL	pnp	V ₀₈₀ =80 B; I _C =100 мA; P _D =200 мBr; h ₂₁ =125250; f _T >100 MΓц	SOT323,SC70	
3B	BC856B	CDIL	ono	V _{GRO} =80 B; I _G =100 mA; P _D =310 mBr; h ₂₁ =200450; f _T >150 MFu	SOT23.SOD23	
3B	BC856B	TOSH	ono	V _{DB0} =80 B; I _C =100 MA; P _D =150 MBr; h ₂₁ =220475; f _T =300 MFu	SOT23,SOD23	F10 F1 F1
3B	BC856B	DIODS	ono	V ₀₈₀ =80 B; I _C =100 мА; Р _D =300 мВт; h ₂₁ =220475; f _T >100 МГц	SOT23,SOD23	10001000000
3B	BC856B	VISH	ono	V _{csn} =80 B; I _c =100 мA; P _D =310 мBr; h ₂₁ =200450; f _T >150 MΓц	SOT23,SOD23	19800001 103
3B	BC856B	III	ono	V _{CR0} =80 B; I _C =100 мА; P _D =310 мВт; h ₂₁ =200450; f _T >150 МГц	SOT23,SOD23	
	BC856BF	PHIL	ono	V_{C80} =80 B; I_C =100 mA; P_D =250 mBr; h_{21} =220475; f_T >100 MFu	SOT490.SC89	
3B						





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
3B	BC856BT	PHIL	pnp	V _{CB0} =80 B; I _C =100 мА; P _D =150 мВт; h ₂₁ =220475; f _T >100 МГц	S0T416,SC75A	B·E·C
3B	FMMT918	ZETEX	non	V _{CR0} =30 B; I _C =100 mA; P _D =330 mBT; h ₂₁ >20; f _T >600 MF _U	SOT23,SOD23	B·E·C
3B	TMPT918	ALLEG	non	V _{CB0} =30 B; I _{CB0} <10 нА; h ₂₁ > 20; V _{CE(set)} < 0.4 B; f ₁ > 600 МГц	SOT23,SOD23	B·E·C
3B-	BC856BW	PHIL	pnp	V _{CR0} =80 B; I _C =100 MA; P _D =200 MBT; h ₂₁ =220475; f _T >100 MFu	SOT323,SC70	B·E·C
3 B p	BC856B	PHIL	pnp	V _{CB0} =80 B; I _C = 100 мА; P ₀ =250 мВт; h ₂₁ =220475; f ₁ >100 МГц	SOT23,SOD23	B·E·C
3BR	BC856BR	PHIL	pnp	V _{CB0} =65B; I _C =100 MA; P _D =200 MBT; h ₂₁ =475; f _T >100 MFц	SOT23,SOD23	E·B·C
3Bs	BC856B	INF	pnp	V _{CR0} =80 B; I _C =100 mA; P _D =330 mBr; h _{D1} =220475; f _T =250 MFu,	SOT23,SOD23	B·E·C
3Bs	BC856BT	INF	onp	V _{CR0} =80 B; I _C =100 mA; P _D =250 mBT; h ₂₁ =220475; f _T =250 MFu	SOT416.SC75A	A 150 MA
3Bs	BC856BW	INF	pnp	V _{CR0} =80 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =220475; f _T =250 MFu	SOT323,SC70	
3Bt	BC856B	PHIL	onp	V _{CR0} =80 B; I _C =100 MA; P _D =250 MBr; h _{Cl} =220475; F _T >100 MFц	SOT23,SOD23	
3Bt	BC856BW	PHIL	pnp	V _{CRD} =80 B; I _C =100 MA; P _D =200 MBT; I _{D2} =220475; f _T >100 MFu	SOT323,SC70	
3C	FMMTA20R	ZETEX	non	V _{CR0} =40 B; I _C =100 MA; P _D =330 MBT; h ₂₁ =40400; f _T >125 MFu	SOT23.SOD23	100000000000000000000000000000000000000
3D	BC856	CDIL	pnp	V _{CB0} =80 B; I _C =100 мА; P _D =250 мВт; h ₂₁ =125800; f _T >100 МГц	SOT23,SOD23	100000000000000000000000000000000000000
3D	MMBTH81LT1	MOT	ono	V _{CB0} -80B; I _C -100 мА, Р _D -250 мВ1, I _{R21} -125600, I _T > 100 мI ц V _{CB0} -20B; P _D -300 мВт; I _{P21} >60; I _T >600 МГц	SOT23,SOD23	200000000000000000000000000000000000000
3D-	BC856W	PHIL		V _{CB0} -80B; I _C =100 mA; P _D =200 mBT; h ₂₁ =125800; f _T >100 MFu	S0T323,SC70	20 20 20
		-	pnp		-	
3Dp	BC856	PHIL	pnp	V _{CB0} -80 B; I _C =100 мА; P _D =250 мВт; h ₂₁ =125800; f _T >100 МГц	SOT23,SOD23	
3Dt	BC856	PHIL	pnp	V _{C80} =80 B, I _C =100 мА; P _D =250 мВт; h ₂₁ =125800; f _T >100 МГц	SOT23,SOD23	
3Dt	BC856W	PHIL	pnp	V _{CB0} =80 B; I _G =100 MA; P _D =200 MBT; h ₂₁ =125800; f _T >100 MFц	SOT323,SC70	
3E	BC857A	CDIL	pnp	V _{CB0} =50 B; I _C =100 мA; P _D =310 мВт; h ₂₁ =110220; f _T >150 МГц	SOT23,SOD23	7.007.070
3E	BC857A	TOSH	pnp	V _{CB0} =50 B; I _C =100 мА; P _D =150 мВт; h ₂₁ =125250; f _T =300 МГц	SOT23,SOD23	127.50 (2)
3E	BC857A	VISH	pnp	V _{CB0} =50 B; I _C =100 мА; P _D =310 мВт; h ₂₁ =110220; f _T >150 МГц	SOT23,SOD23	
3E	BC857A	DIODS	pnp	V_{CB0} =50B; I_C =100mA; P_D =300mBT; h_{21} =110220; f_T >100M Γ_{II}	SOT23,SOD23	
3E	BC857AF	PHIL	pnp	V _{CB0} =50 B; I _C =100 мА; P _D =250 мВт; h ₂₁ =125250; f _T >100 МГц	SOT490,SC89	B-E-C
3E	BC857ALT1	MOT	pnp	V_{CB0} =50B; I_C =100mA; P_D =300mBT; h_{21} =125250; f_T >100MF μ	SOT23,SOD23	B·E·C
3E	BC857AT	PHIL	pnp	V_{CB0} =50 B; I_C = 100 mA; P_D = 150 mB1; h_{21} = 125250; f_T > 100 MF μ	SOT416,SC75A	B·E·C
3E	FMMTA42	ZETEX	non	V_{CB0} =300 B; I_C =200 mA; P_D =330 mBt; h_{21} >40; f_T >50 MFu	SOT23,SOD23	B-E-C
3E	KST10	SAMS	npn	V _{CB0} =30 B; P _D =350 мВт; h ₂₁ >60; f _T >650 МГц	SOT23,SOD23	B·E·C
3E	MMBTH10	MOT	npn	V _{CB0} =30 B; P _D =300 мВт; h ₂₁ >60; f _T >650 МГц	SOT23,SOD23	B·E·C
3E-	BC857AW	PHIL	pnp	V _{CB0} =50 B; I _C =100 мА; P ₀ =200 мВт; h ₂₁ =125250; f _T >100 МГц	SOT323,SC70	B·E·C
3EM	MMBTH10LT1	MOT	non	V _{CR0} =30 B; P _D =300 mBT; h ₂₁ >60; f _T >650 MF _U	SOT23,SOD23	B·E·C
3Ep	BC857A	PHIL	pnp	V _{CB0} =50 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ =125250; f _T >100 МГц	SOT23,SOD23	B-E-C
3ER	BC857AR	PHIL	pnp	V _{CB0} =45B; I _C =100 mA; P ₀ =250 mBT; h ₂₁ =220; f _T >150 MFu	SOT23.SOD23	E·B·C
3Es	BC857A	INF	pnp	V _{CR0} =50 B; I _C =100 mA; P _D =330 mBr; h ₂₁ =125250; f _T =250 MFu,	SOT23,SOD23	B·E·C
3Es	BC857AW	INF	pnp	V _{CR0} =50 B; I _C =100 mA; P _D =250 mBr; I ₂₁ =125250; f _T =250 MFu	SOT323.SC70	0.00.00
3Et	BC857A	PHIL	pnp	V _{CRD} =50B; I _C =100 MA; P _D =250 MBT; h ₂₁ =125250; f _T >100 MFu	SOT23,SOD23	
3Et	BC857AW	PHIL	ono	V _{CB0} =50 B, I _C =100 мА; Р ₀ =200 мВт; h ₂₁ =125250; f _T >100 МГц	SOT323.SC70	
3EZ	FMMTH10	ZETEX	non	V _{CBD} -30B; I _C =25 MA; P _D =230 MBT; I _{P21} =123230, I _T >100 MILL	SOT23,SOD23	
3F	BC857B	CDIL	pnp	V _{CR0} =50B; I _C =100мA; P _D =310мBт; I _{P2} =200450; f _T >150МГц	SOT23,SOD23	100 100 100 100
3F	BC857B	DIODS		V _{CB0} =50B; I _C =100мA; P _D =310мB1; I _{I2} 1=200450; I _T >130МIц V _{CB0} =50B; I _C =100мA; P _D =300мBт; I _{D2} 1=200450; I _T >100МГц	SOT23,SOD23	20000000
3F	BC857B		pnp	000	SOT23,SOD23	
3F	100000000000000000000000000000000000000	TOSH	pnp	V _{CB0} =50 B; I _C =100 mA; P _D =150 mB; h ₂₁ =220475; f _T =300 MFµ		
	BC857B	VISH	pnp	V _{CB0} =50 B; I _G =100 MA; P _D =310 MBT; h ₂₁ =200450; f _T >150 MFц	SOT23,SOD23	
3F	BC857B	ZETEX	pnp	V _{CB0} =50 B; I _C =100 mA; P _D =330 mBT; h ₂₁ =220475; f _T >150 MFц	SOT23,SOD23	
3F	BC857BF	PHIL	pnp	V_{CB0} =50 B; I_C =100 mA, P_D =250 mBT; h_{21} =220475; f_T >100 MFu	SOT490,SC89	
3F	BC857BLT1	MOT	pnp	V_{CB0} =50 B; I_C =100 mA; P_D =300 mBT; h_{21} =220475; f_T >100 MF $_{II}$	SOT23,SOD23	100,000,000
3F	BC857BT	PHIL	pnp	V _{CB0} =50 B; I _C = 100 мА; P _D = 150 мВт; h ₂₁ =220475; f _T > 100 МГц	SOT416,SC75A	
3F-	BC857BW	PHIL	pnp	V _{CB0} =50 B; I _C = 100 мА; P ₀ =200 мВт; h ₂₁ =220475; f ₁ > 100 МГц	SOT323,SC70	12 80 10
3Fp	BC857B	PHIL	pnp	V _{CB0} =50 B; I _C =100 мA; P ₀ =250 мВт; h ₂₁ =220475; f _T > 100 МГц	SOT23,SOD23	
3FR	BC857BR	PHIL	pnp	V _{CB0} =45 B; I _C = 100 мА; P _D =200 мВт; h ₂₁ =475; f _T > 150 МГц	SOT23,SOD23	E-B-C
3Fs	BC857B	INF	pnp	V _{CB0} =50 B; I _C = 100 мА; P _D =330 мВт; h ₂₁ =220475; f _T =250 МГц	SOT23,SOD23	B·E·C
3Fs	BC857B	SIEM	pnp	V _{CB0} =50 B; I _C = 100 мА; P _D =330 мВт; h ₂₁ =220475; f _T >150 МГц	SOT23,SOD23	B·E·C
3Fs	BC857BW	SIEM	pnp	V _{CBO} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =220475; f _T =250 МГц	SOT323,SC70	B.E.C
3Ft	BC857B	PHIL	pnp	V _{CR0} =50 B; I _C =100 mA; P _D =250 mBT; h ₂₁ =220475; f _T >100 MFu	SOT23,SOD23	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
3Ft	BC857BW	PHIL	pnp	V _{CR0} =50 B; I _C =100 mA; P _D =200 mBt; h ₂₁ =220475; f _T >100 MFu	SOT323,SC70	B-E-C
G	BC857C	CDIL	pnp	V _{гал} = 50 B; I _C = 100 мA; P _D = 310 мВт; h ₂₁ = 420800; f _T > 150 МГц	SOT23,SOD23	B-E-C
3G	BC857C	TOSH	pnp	V ₀₈₀ =50 B; I _C =100 мA; P _D =150 мВт; h ₂₁ =420800; f _T >300 МГц	SOT23,SOD23	B-E-C
3G	BC857C	DIODS	ono	V _{CR0} =50 B; I _C =100 MA; P _D =150 MBT; h ₂₁ =420800; f _T >300 MFu	SOT23,SOD23	B-E-C
3G	BC857C	VISH	ono	V _{CR0} =50 B; I _C =100 MA; P _D =310 MBT; h ₂₁ =420800; f _T >150 MFц	SOT23,SOD23	B·E·C
3G	BC857C	ZETEX	onp	V ₀₈₀ =50 B; I _C =100 мA; P _D =330 мВт; h ₂₁ =420800; f _T >150 МГц	SOT23.SOD23	100000000000000000000000000000000000000
3G	BC857CF	PHIL	onp	V _{CB0} =50 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =420800; f _T >100 MFu	SOT490,SC89	B·E·C
3G	BC857CT	PHIL	ono	V _{CR0} =50 B; I _C =100 мA; P _D =150 мBт; h ₂₁ =420800; f _T >100 MΓι ₄	SOT416,SC75A	
3G	BC857CT	DIODS	pnp	V _{CB0} =50 B; I _C =100 мA; P _D =310 мBт; h ₂₁ =420800; f _T >150 МГц	SOT523	B·E·C
3G	MMBTH11	FAIR	ngn	V ₀₈₀ =30 B; I ₀ =50 mA; P ₀ =3225 mBr; h ₂₁ >60; f ₁ <650 MFu	SOT23,SOD23	
3G-	BC857CW	PHIL	onp	V _{DR0} =50 B; I _C =100 MA; P _D =200 MBT; h ₂₁ =420800; f _T >100 MFu	SOT323,SC70	
3Go	BC857C	PHIL	ono	V _{C80} =50 B; I _C =100 MA; P _D =250 MB; h ₂₁ =420800; f _T >100 MF _U	SOT23.SOD23	17503200000
3GR	BC857CR	PHIL	prip	V _{CR0} =35 В; I _C =100 мА; P _D =250 мВт; h ₂₁ =420500, гу > 150 МГц	SOT23,30D23	
3Gs	BC857CR	INF	ono	V _{C80} =50B; I _C =100 MA; P _D =330 MBr; h ₂₁ =420800; f _T =250 MF _U	SOT23,SOD23	0.0000 000
	0.0000000000000000000000000000000000000				-	100000
3Gs	BC857CW	INF	pnp	V _{CB0} =50 B; I _C =100 мA; P _D =250 мBт; h ₂₁ =420800; f _T =50 MΓц	SOT323,SC70	
3Gt	BC857C	PHIL	pnp	V _{CBO} =50 B; I _C =100 мА; P _D =250 мВт; h ₂₁ =420800; f _T >100 МГц	SOT23,SOD23	
3Gt	BC857CW	PHIL	pnp	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBr; h ₂₁ =420800; f ₁ >100 MFц	SOT323,SC70	
3H	BC857	CDIL	pnp	V_{C80} =50 B; I_C =100 MA; P_0 =250 MBT; h_{21} =125800; f_T >100 M Γ_{IJ}	SOT23,SOD23	70070070
3H	BC857W	PHIL	pnp	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBr; h_{21} =125800; f_T >100 M Γ_{LL}	SOT323,SC70	TOTAL CO.
3H	MMBTH30	NS	npn	V _{C80} =20 B; I _C =50 мА; P _D =350 мВт; h ₂₁ >200; f _T >300 МГц	SOT23,SOD23	32232 22
ЗНр	BC857	PHIL	pnp	V _{C80} =50 B; I _C =100 мА; P _D =250 мВт; h ₂₁ =125800; f _T >100 МГц	SOT23,SOD23	
3J	BC858A	CDIL	pnp	V _{G80} =30 B; I _C =100 мА; Р ₀ =310 мВт; h ₂₁ =110220; f _T >150 МГц	SOT23,SOD23	
3J	BC858A	VISH	pnp	V_{C80} =30B; I_C =100 mA; P_D =310 mBT; h_{21} =110220; f_T >150 M Γ_{II}	SOT23,SOD23	
3J	BC858A	ZETEX	pnp	V_{C80} =30 B; I_C =100 mA; P_D =330 mBt; h_{21} =125250; f_T >150 M Γ_{II}	SOT23,SOD23	B-E-C
3J	BC858A	DIODS	pnp	V_{C80} =30 B; I_C =100 MA; P_D =300 MBr; h_{21} =125250; f_T >100 M Γ_{II}	SOT23,SOD23	B-E-C
3J	BC858AF	PHIL	pnp	V_{C80} =30 B; I_C =100 mA; P_D =250 mBr; h_{21} =125250; f_T >100 MFu	SOT490,SC89	B-E-C
3J	BC858ALT1	MOT	pnp	V_{CB0} =30 B; I_C =100 mA; P_D =300 mBr; h_{21} =125250; f_T >100 M Γ_{II}	SOT23,SOD23	B-E-C
3J	BC858AW	PHIL	pnp	V_{C80} =30 B; I_C =100 mA; P_0 =200 mBr; h_{21} =125250; f_T >100 M Γ_{II}	SOT323,SC70	B·E·C
3J	MMBTH69	MOT	pnp	V_{080} =15B; P_0 =300 MBT; h_{21} =30300; f_T >2000 MFц	SOT23,SOD23	B-E-C
3J	RB706F-40	ROHM	shd×2	$V_B \le 40 \text{ B}; I_E \le 30 \text{ mA}; V_E (I_E = 1 \text{ mA}) \le 370 \text{ mB}; C_D = 2 \pi \Phi$	SOT323,SC70	A1 · K1 A2 · K2
3Jp	BC858A	PHIL	pnp	V _{CB0} =30 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =125250; f _T >100 МГц	SOT23,SOD23	B·E·C
3JR	BC858AR	PHIL	pnp	V _{CBO} =30 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =220; f _T >150 МГц	SOT23,SOD23	E-B-C
3Js	BC858A	INF	pnp	V _{сво} =30 B; I _C =100 мA; P _D =330 мВт; h ₂₁ =125250; f _T =250 МГц	SOT23,SOD23	B-E-C
3Js	BC858AW	SIEM	pnp	V _{C80} = 30 B; I _C = 100 мA; P _D = 250 мВт; h ₂₁ = 125250; f _T = 250 МГц	SOT323,SC70	B-E-C
3Jt	BC858A	PHIL	pnp	V _{CB0} * 30 B; I _C * 100 MA; P _D * 250 MBT; h ₂₁ * 125250; f _T > 100 MFu	SOT23,SOD23	B·E·C
3K	BC858B	CDIL	pnp	V_{G80} =30 B; I_C =100 mA; P_0 =310 mBr; h_{21} =200450; f_T >150 MFu	SOT23,SOD23	
3K	BC858B	TOSH	pnp	V _{csn} =30 B; I _c =100 мA; P _n =150 мВт; h ₂₁ =220475; f _T =300 МГц	SOT23,SOD23	B·E·C
3K	BC858B	DIODS	pnp	V _{CR0} =30 B; I _C =100 mA; P _D =300 mBτ; h ₂₁ =220475; f _T >100 MΓι ₄	SOT23,SOD23	100/03/19/35
3K	BC858B	VISH	ono	V ₀₈₀ =30 B; I _C =100 mA; P _D =310 mBr; h ₂₁ =200450; f _T >150 MFц	SOT23,SOD23	
3K	BC858B	ZETEX	pnp	V _{G80} =30 B; I _G =100 mA; P _D =330 mBr; h ₂₁ =220475; f _T >150 MFu	SOT23,SOD23	
3K	BC858BF	PHIL	onp	V _{GR0} =30 B; I _G =100 mA; P _D =250 mBr; h ₂₁ =220475; f _T >100 MFц	SOT490,SC89	
3K	BC858BLT1	MOT	pnp	V _{DBD} =30 B; I _C =100 MA; P _D =300 MBr; h ₂₁ =220475; f _T >100 MFц	SOT23,SOD23	
3K	BC858BW	PHIL	onp	V _{C80} =30 B; I _C =100 mA; P _D =200 mBr; h ₂₁ =220475; f _T >100 MFu	SOT323,SC70	
3Kp	BC858B	PHIL	prip	V _{CB0} =30 B; I _C =100 MA; P _D =250 MB; h ₂₁ =220475; f _T >100 MF _U	SOT23,SOD23	
3KR	BC858BR	PHIL	pnp	V _{DR0} =30 B; I _C =100 MA; P _D =200 MBT; h ₂₁ =475; f _T >150 MFu	SOT23,SOD23	1,000,000
3Ks	BC858B	SIEM	prip	V _{CB0} =30 B; I _C =100 мA; P _D =200 мB; h ₂₁ =473; ту 130 мПц V _{CB0} =30 B; I _C =100 мA; P _D =330 мВг; h ₂₁ =220475; f _T =250 МГц	SOT23,30D23	100002 20
3Ks	BC858BW	SIEM	-	V _{CBB} -30 B; I _C -100 мА; P _D -350 мВт; I _{R2} -220475; I _T -250 мГц V _{CBB} -30 B; I _C -100 мА; P _D -250 мВт; I _{P2} -220475; I _T -250 МГц	SOT323.SC70	10000 100
3Kt	BC858B	PHIL	pnp		_	
			pnp	V _{CBO} =30 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =220475; f _T >100 mFu	SOT23,SOD23	
3L	BC858C	CDIL	pnp	V _{C80} =30 B; I _C =100 MA; P _D =310 MBT; h ₂₁ =420800; f _T >150 MFц	SOT23,SOD23	
3L	BC858C	TOSH	pnp	V _{C80} =30 B; I _C =100 mA; P _D =150 mBr; h ₂₁ =420800; f _T =300 MFц	SOT23,SOD23	
3L	BC858C	VISH	pnp	$V_{CB0}=30 \text{ B}; I_C=100 \text{ MA}; P_D=310 \text{ MBr}; h_{21}=420800; f_T>150 \text{ MFL}$	SOT23,SOD23	100000000000000000000000000000000000000
3L	BC858C	ZETEX	pnp	V_{CB0} =30 B; I_C =100 mA; P_D =330 mBr; h_{21} =420800; f_T >150 MFu	SOT23,SOD23	R.E.C





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
3L	BC858C	DIODS	pnp	V _{CB0} =30 B; I _C =100 mA; P _D =300 mBT; h ₂₁ =420800; f _T >100 MFu,	S0T23,S0D23	B·E·C
3L	BC858CF	PHIL	pnp	V _{CRD} =30B; I _C =100 мА; P _D =250 мВт; h ₂₁ =420800; f _T >100 МГц	SOT490,SC89	B·E·C
3L	BC858CLT1	MOT	pnp	V _{CB0} =30 B; I _C =100 мA; P ₀ =300 мВт; h ₂₁ =420800; f _T >100 МГц	SOT23,SOD23	B·E·C
3L	BC858CW	PHIL	pnp	V _{сяп} =30B; I _с =100 мА; P _п =200 мВт; h ₂₁ =420800; f _T >100 МГц	S0T323.SC70	B-E-C
3Lp	BC858C	PHIL	pnio	V _{сво} =30 B; I _с = 100 мА; P _о =250 мВт; h ₂₁ =420800; f _T > 100 МГц	SOT23,SOD23	B·E·C
3LR	BC858CR	PHIL	pnp	V _{сво} =30 B; I _с =100 мA; P _о =250 мВт; h ₂₁ =800; f _f >150 МГц	SOT23,SOD23	E·B·C
3Ls	BC858C	SIEM	pnp	V _{CR0} =30 B; I _C =100 мA; P _D =330 мВт; h ₂₁ =420800; f _T =250 МГц	SOT23,SOD23	B·E·C
3Ls	BC858CW	SIEM	pnp	V _{CR0} =30 B; I _C =100 mA; P _D =250 mBT; h ₂₁ =420800; f _T =250 MFu	S0T323,SC70	
3Lt	BC858C	PHIL	pnip	V _{CR0} =30 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =420800; f _T >100 MΓц	SOT23.SOD23	
3M	2SC4808	PAN	non	V _{C80} =15B; I _C =80мA; P _D =125мВт; h ₂₁ =50300; f _T >5ГГц	S0T416.SC75A	
3M	2SC4835	PAN	non	V _{CR0} =15B; I _C =80 мA; P _D =150 мBτ; h ₂₁ =50200; fr>5 ΓΓu	SOT323,SC70	
3M	BC858	CDIL	pnp	V _{CB0} =30B; I _C =100мA; P _D =250мBт; h ₂₁ =125800; f _T >100МГц	SOT23.SOD23	100000000000000000000000000000000000000
3M	BC858W	PHIL	prip	V _{CBD} =30B; I _C =100 MA; P _D =200 MBT; h ₂₁ =125800; f _T >100 MFц	SOT323,SC70	0.0000000000000000000000000000000000000
3m	FMMT5087R	ZETEX	ono	V _{CB0} =50B; I _C =100MA; P _D =200MB; n ₂₁ =123600; r _T >100 MIL _L V _{CB0} =50B; I _C =100MA; P _D =330MBr; h ₂₁ =200600; f _T >40 MIL _L	SOT23.SOD23	000000000000000000000000000000000000000
ЗМр	BC858	PHIL	1 1	V _{CR0} -30 B; I _C =100 MA; P _D =350 MB1; I _{D1} =250600; I _T >40 MIQ V _{CR0} =30 B; I _C =100 MA; P _D =250 MB1; I _{D1} =125800; I _T >100 MIQ	SOT23,SOD23	
			pnp			
3Mt	BC858	PHIL	pnp	V _{CBO} =30 B; I _C =100 mA; P _D =250 mBτ; h ₂₁ =125800; f _T >100 MΓц	SOT23,SOD23	
3N	2SK620	PAN	nMOS	V _{DS} =50B; I _D =100 mA; P _D =150 mBT; R _{DS(on)} <50 Om	SOT346,SC59	
3N	2SK664	PAN		V _{DS} =50B; I _D =100 мA; P _D =150 мBT; R _{DS(on)} < 50 Oм	S0T323,SC70	
3N	MMBT3906	VISH	pnp	V _{CB0} =40 B; I _C = 100 мA; P _D =200 мВт; h ₂₁ = 100300; f _T > 250 МГц	SOT23,SOD23	
3N	MMBT4402	NS	pnp	V _{CB0} =40 B; I _C =500 мА; P _D =350 мВт; h ₂₁ >30; f _T >150 МГц	SOT23,SOD23	
30	2SK621	PAN		V _{DS} =20 B; I _D =100 мА; P _D =150 мВт; R _{DS(on)} < 50 Ом	SOT346,SC59	
30	2SK665	PAN	nMOS	V _{DS} =20 B; I _D =100 мA; P _D =150 мВт; R _{DS(on)} <50 Ом	SOT323,SC70	
3P	FMMT2222AR	ZETEX	npn	V_{CB0} =75B; I_C =600mA; P_D =330mBT; h_{21} =120360; f_T >300M Γ_{II}	SOT23,SOD23	B·E·C
3P	FMT2222AR	ZETEX	non	V_{CB0} =75B; I_C =800 mA; P_D =500 mBT; h_{21} >30	SOT23,SOD23	E·B·C
3R	MMBT5571	NS	pnp	f _T =850 ΜΓιμ	SOT23,SOD23	B·E·C
3R	PDTA124EEF	PHIL	Dpnp	V _{CB0} =50 B; I _C =100 mA; P _D =250 mBr; h ₂₁ >60; 22 kOm/22 kOm	SOT490,SC89	B·E·C
3S	2SC4805	PAN	npn	V _{CB0} =15B; I _C =65мA; P _D =150мBт; h ₂₁ =50300; f _T >7ГГц	SOT323,SC70	B·E·C
3S	MMBT5551	ON	npn	V _{CB0} =180 B; I _C =200 мА; P _D =350 мВт; h ₂₁ =80250; f _T >300 МГц	SOT23,SOD23	B·E·C
3S	MMBT5551	VISH	npn	V _{CB0} =180B; I _C =200 мA; P _D =350 мВт; h ₂₁ =80250; f _T >300 МГц	SOT23,SOD23	B·E·C
3S	MMBT5551	NS	non	V _{GB0} =160 B; I _C =600 MA; P _D =300 MBT; h ₂₁ =80250	SOT23,SOD23	B·E·C
3T	HT3	ZETEX	pnp	V _{CBB} =90B; I _C =100 mA; P _D =330 mBT; h ₂₁ >30	SOT23,SOD23	B·E·C
3U	2SC3967U	PAN	non	V _{CBD} =30 B; I _C =20 мA; P _D =200 мВт; h ₂₁ =40200; f _T =1.5 ГГц	SOT23.SOD23	B·E·C
3V	BC857AT	DIODS	pnp	V _{сво} =50 B; I _с =100 мА; P _п =300 мВт; h ₂₁ =125250; f _T >100 МГц	S0T523	B·E·C
3V0	PZM3.0NB	PHIL	dz	V _x (I _{zz} =5 MA)=2.83.2B; Z _{zz} (I _{zz} =5 MA)<95 OM	SOT346,SC59	
3V3	PZM3.3NB	PHIL	dz	V ₂ (I ₂₁ =5 MA)=3.13.5B; Z ₂₁ (I ₂₁ =5 MA)<95 Om	SOT346,SC59	
3V6	PZM3.6NB	PHIL	dz	V _Z (I _{ZI} =5 MA)=3.43.8 B; Z _{ZI} (I _{ZI} =5 MA)<90 Om	SOT346,SC59	
3V9	PZM3.9NB	PHIL	dz	V _X (₂₇ -5 MA)-3.43.6B, Z ₂ (₁₂₇ -5 MA) < 90 OM	SOT346,SC59	
3W	BC857BT	DIODS	pnp	V _{CB0} =50B; I _C =100мA; P _D =330мBт; h ₂₁ =220475; f _T >150МГц	SOT523	B-E-C
3W	FMMTA12	ZETEX		V _{CB0} =30 B; I _C =100 MA; P _D =330 MBT; N ₂₁ =220475; T _T >150 MI L V _{CB0} =20 B; I _C =300 MA; P _D =330 MBT; h ₂₁ >20000	S0T23.S0D23	
1.3X	02CZ4.3		npn	000	-	
		TOSH	dz	$V_Z(I_{ZT}=5 \text{ mA})=4.004.50 \text{ B}; I_L(V_R=1.0 \text{ B})<5 \text{ m/A}; Z_{ZT}(I_{ZT}=0.5 \text{ mA})<1000 \text{ Om}$	SOT346,SC59	
1.7X	02CZ4.7	TOSH	dz	V _Z (I _{ZT} =5 mA)=4.404.90 B; I _L (V _R =1.0 B) < 5 mKA; Z _{ZT} (I _{ZT} =0.5 mA) < 1000 Om	SOT346,SC59	
10p	PMBFJ110	PHIL	nFET	V _{DS} =25B; I _{DSS} >10 MA; P _D =250 MBT; R _{DS(on)} <18 OM	SOT23,SOD23	
10t	PMBFJ110	PHIL	nFET	V _{DS} =25B; I _{DSS} >10 mA; P _D =250 mBT; R _{DS(on)} <18 Om	SOT23,SOD23	
IOW	PMBFJ110	PHIL	nFET	V _{DS} =25B; I _{DSS} >10 мA; P _D =250 мB⊤; R _{DS(on)} <18 Ом	SOT23,SOD23	100000
41	PDTA143XEF	PHIL	Dpnp	V _{CB0} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ >50; 4.7 кОм/10 кОм	SOT490,SC89	10.766
413	FMMT413	ZETEX	npn	V_{CB0} =150B; I_C =100 mA; P_D =330 mBt; $h_{21}>50$; $f_T>150 M\Gamma u$	SOT23,SOD23	
115	FMMT415	ZETEX	npn	V_{CB0} =260 B; I_C =500 mA; P_0 =330 mBt; h_{21} >25; f_T >40 MFu	SOT23,SOD23	
117	FMMT417	ZETEX	npn	V_{CB0} =320 B; I_C =500 mA; P_0 =330 mBt; h_{21} >25; f_T >40 MFu	SOT23,SOD23	B-E-C
HA	FMMT491A	ZETEX	npn	V_{CB0} =40 B; I_C = 1000 mA; P_0 =500 mBt; h_{21} =300900; f_T > 150 MFu	SOT23,SOD23	B·E·C
11p	PMBFJ111	PHIL	nFET	V _{DS} =40B; I _{DSS} >20 mA; P _D =300 mBT; R _{DS(on)} <30 Om	SOT23,SOD23	D·S·G
11t	PMBFJ111	PHIL	nFET	V _{DS} =40B; I _{DSS} >20 mA; P _D =300 mBT; R _{DS(on)} <30 Om	SOT23,SOD23	D·S·G
11W	PMBFJ111	PHIL	nFET	V _{DS} =40 B; I _{DSS} >20 MA; P _D =300 MBT; R _{DS(pD)} <30 OM	SOT23,SOD23	D·S·G

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
42	BAT54AW	PHIL	shd×2	$V_R < 30B$; $I_F < 200 \text{ mA}$; $V_F (I_F = 1 \text{ mA}) < 320 \text{ mB}$; $C_D < 10 \text{ n}\Phi$; $t_{RR} < 5 \text{ hc}$	SOT323,SC70	K1-K2-A2,A1
42p	PMBFJ112	PHIL	nFET	V _{DS} =40 B; I _{DSS} >5 mA; P _D =300 mBT; R _{DS(on)} <50 Om	SOT23,SOD23	D·S·G
42t	PMBFJ112	PHIL	nFET	V _{DS} =40 B; I _{DSS} >5 мА; P _D =300 мВт; R _{DS(on)} <50 Ом	SOT23,SOD23	D-S-G
42W	PMBFJ112	PHIL	nFET	V _{DS} =40 B; I _{DSS} >5 MA; P _D =300 MBT; R _{DS(pp)} <50 OM	SOT23.SOD23	D-S-G
43	BAS40	VISH	shd	$V_R < 40B$; $I_e < 200 \text{ mA}$; $V_P (I_e = 40 \text{ mA}) < 1.0B$; $I_R < 0.2 \text{ mcA}$; $C_D < 5.0 \text{ n}\Phi$; $t_{PR} < 5 \text{ hc}$	SOT23,SOD23	A·n.c.·K
43	BAS40	DIOT	shd	$V_p < 40B$; $I_e < 200 \text{ mÅ}$; $V_e (I_e = 40 \text{ mÅ}) < 1.0B$; $I_p < 0.2 \text{ mkÅ}$; $C_n < 5.0 \text{ n}\Phi$; $t_{pp} < 5 \text{ Hz}$		A·n.c.·K
43	BAS40	MCS	shd	$V_B < 40B$; $I_E < 200 \text{ mA}$; $V_E (I_E = 40 \text{ mA}) < 1.0B$; $I_B < 0.2 \text{ mcA}$; $C_D < 5.0 \text{ n}\Phi$; $t_{BB} < 5 \text{ Hz}$	SOT23,SOD23	A·n.c.·K
43	BAS40	TSC	shd	V _B <40B; I _F <200 mA; V _F (I _F =40 mA)<1.0B; I _B <0.2 mKA; C _B <5.0 nΦ; t _{BB} <5 hc	SOT23,SOD23	
43	BAS40	GS	shd	V _R <40B; I _F <200 mA; V _F (I _F =40 mA)<1.0B; I _R <0.2 mkA; C _D <5.0 nΦ; t _{RR} <5 hc	SOT23,SOD23	-
43	BAT54CW	PHIL	shd×2	V _B <30 B; I _E <200 mA; V _E (I _E =1 mA)<320 mB; C _D <10 mΦ; t _{BB} <5 hc	-	A1+A2+K1.K2
43	DTC143XE	ROHM	Dnpn	V _{CB0} +50 B; I _C =100 xA; P _D =150 xBT; h ₂₁ >30; f _T >250 MFu; R ₁ /R ₅ -4.7/10 xOx	SOT416,SC75A	
43	DTC143XKA	ROHM	Dnpn	V_{C80}^{-} 50 B; I_C = 100 xA; P_D = 200 xBt; h_{21} > 30; f_T > 250 MFu; R_1/R_2 = 4.7/ 10 xOx	SOT346,SC59	B-E-C
43	DTC143XUA	ROHM	Dnpn	$V_{\rm C80}$:50 S; $I_{\rm C}$ = 100 MA; $P_{\rm D}$ = 200 MB $_{\rm T}$; $h_{\rm 21}$ > 30; $f_{\rm T}$ > 250 M $\Gamma_{\rm U}$; $R_{\rm 1}/R_{\rm 2}$ = 4.7/10 kOM	S0T323,SC70	B-E-C
43p	BAS40	PHIL	shd	V _B <40 B; I _F <120 mA; V _E (I _F =1 mA)<380 mB; C _D <5 πΦ	SOT23,SOD23	A·n.c.·K
43s	BAS40	INF	shd	$V_B < 40 B$; $I_F < 120 mA$; $V_F (I_F = 40 mA) < 1 B$; $I_R < 1.0 m kA$; $C_D < 5 \pi \Phi$	SOT23,SOD23	A·n.c.·K
43s	BAS40	SIEM	shd	$V_R < 40 B$; $I_F < 120 mA$; $V_F (I_F = 40 mA) < 1.0 B$; $I_R < 1.0 m kA$; $C_D < 5.0 n \Phi$	SOT23,SOD23	A·n.c.·K
43V	PZM43NB	PHIL	dz	V _Z (I _{ZT} =2 mA)=40.046.0 B; Z _{ZT} (I _{ZT} =2 mA) < 80 Om	SOT346,SC59	A·n.c.·K
43X	02CZ43	TOSH	dz	V ₂ (I _{ZT} =2 mA)=40.0045.00B; I _L (V _R =33B)<0.5mrA	SOT346,SC59	A·n.c.·K
44	BAS4004	VISH	shd×2	$V_R < 40 B$; $I_F < 200 mA$; $V_E (I_F = 40 mA) < 1.0 B$; $I_R < 0.2 mkA$; $C_D < 5.0 n\Phi$; $t_{PR} < 5 hc$	SOT23,SOD23	A1-K2-K1,A2
44	BAS40-04	DIOT	shd×2	$V_R < 40 \text{ B}; I_F < 200 \text{ mA}; V_F (I_F = 40 \text{ mA}) < 1 \text{ B}; I_R < 1.0 \text{ m/A}; C_D < 5 \text{ m}\Phi; I_{RR} < 5 \text{ Hc}$	SOT23,SOD23	A1 · K2 · K1, A2
44	BAS40-04	MCS	shd×2	$V_B < 40 \text{ B}; I_F < 200 \text{ mA}; V_F (I_F = 40 \text{ mA}) < 1 \text{ B}; I_R < 1.0 \text{ mkA}; C_D < 5 \text{ n}\Phi; t_{RR} < 5 \text{ Hz}$	SOT23,SOD23	A1 · K2 · K1, A2
44	BAS40-04	TSC	shd×2	$V_R < 40 B$; $I_F < 200 mA$; $V_F < I_F = 40 mA$) $< 1 B$; $I_R < 1.0 mkA$; $C_D < 5 \pi \Phi$; $t_{RR} < 5 hc$	SOT23,SOD23	A1-K2-K1,A2
44	BAS40-04	GS	shd×2	$V_B < 40 B$; $I_F < 200 mA$; $V_F (I_F = 40 mA) < 1 B$; $I_B < 1.0 mkA$; $C_D < 5 \pi\Phi$; $t_{BB} < 5 Hc$	SOT23,SOD23	A1-K2-K1,A2
44	BAT54SW	PHIL	shd×2	V _R <30 B; I _F <200 mA; V _F (I _F =1 mA)<320 mB; C _D <10 nΦ; t _{RR} <5 Hc	SOT323,SC70	A1-K2-K1,A2
449	FMMT449	ZETEX	npn	V _{CB0} =50 B; I _C =1000 мА; P _D =500 мВт; h ₂₁ =100300; f _T >150 МГц	SOT23,SOD23	B-E-C
44p	BAS4004	PHIL	shd×2	V _B <40 B; I _F <120 mA; V _F (I _F =1 mA)<380 mB; C _D <5 nΦ	SOT23,SOD23	A1-K2-K1,A2
44s	BAS4004	SIEM	shd×2	V _B <40 B; I _F < 120 мA; V _F (I _F =40 мA)<1.0 B; I _B <1.0 мкA; С _П <5.0 пФ	SOT23,SOD23	A1-K2-K1,A2
44s	BAS40-04	INF	shd×2	V _B <40 B; I _E <120 mA; V _E (I _E =40 mA)<1 B; I _B <1.0 mкA; C _D <5 πΦ	SOT23,SOD23	A1-K2-K1,A2
44s	BAS40-04	INF	shd×2	V _B <40B; I _E <120 mA; V _E (I _E =40 mA)<1B; I _B <1.0 mkA; C _D <5 πΦ	SOT23,SOD23	A1-K2-K1,A2
44s	BAS4004W	SIEM	shd×2	V _R <40B; I _E <120mA; V _E (I _E =15mA)<1.0B; I _R <1.0mkA; C _D <5.0nΦ	SOT323,SC70	A1-K2-K1,A2
44s	BAS40-04W	INF	shd×2	V _B <40 B; I _E <120 мA; V _E (I _E =40 мA) < 1 B; I _B <1.0 мкА; С _D <5 пФ	SOT323,SC70	A1-K2-K1,A2
45	BAS4005	VISH	shd×2	V _B =40 B; I _E =200 mA; P _D =200 mBr; t _{BB} <5 Hc	SOT23,SOD23	A1-A2-K1,K2
45	DTC124XE	ROHM	Dnpn	V _{CR0} =50 B; I _C =100 MA; P _D =150 MBT; h ₂₁ >68; f _T >250 MFu; R ₁ /R ₂ =22/47 KOM	SOT416,SC75A	B-E-C
45	DTC124XKA	ROHM	Dnpn	V _{G80} =50 B; I _C =100 мА; P ₀ =200 мВт; h ₂₁ >68; f ₁ >250 МГц; R ₁ /R ₂ =22/47 кОм	SOT346,SC59	B·E·C
45	DTC124XUA	ROHM	Dnpn	V ₀₈₀ =50 B; I _C =100 мА; P ₀ =200 мВт; h ₂₁ >68; f ₁ >250 МГц; R ₁ /R ₂ =22/47 кОм	SOT323,SC70	B·E·C
451	FMMT451	ZETEX	npn	V _{CR0} = 80 B; I _C = 1000 MA; P _D = 500 MBT; h _{P1} = 50150; f _T > 150 MFu	SOT23,SOD23	B-E-C
455	FMMT455	ZETEX	npn	V _{GBO} =160 B; I _G =1000 мА; P _D =500 мВт; I _{D-1} =100300; I _T >100 МГц	SOT23,SOD23	B-E-C
458	FMMT458	ZETEX	npn	V _{G80} =400 B; I _C =225 мА; P _D =500 мВт; h ₂₁ =100300; f ₁ >50 МГц	SOT23,SOD23	B-E-C
459	TMPD459	ALLEG	dl	I _E <500 mA; V _{BR} >200 B; V _E (I _E =3 mA) 1.0 B; I _B <25 μA; C _O <6.0 πΦ	SOT23,SOD23	A•n.c.•K
45p	BAS4005	PHIL	shd×2	$V_B < 40 B$; $I_E < 120 \text{ mA}$; $V_E (I_E = 1 \text{ mA}) < 380 \text{ mB}$; $C_D < 5 \text{ n}\Phi$	SOT23,SOD23	A1 • A2 • K1.K2
45s	BAS4005	SIEM	shd×2	V _R <40B; I _E <120 mA; V _E (I _E =40 mA)<1.0 B; I _R <1.0 mκA; C _D <5.0 πΦ	SOT23,SOD23	
45s	BAS40-05	INF	shd×2	V _R <40 B; I _E <120 мA; V _E (I _E =40 мA) <1 B; I _B <1.0 мкА; С _D <5 пФ	SOT23,SOD23	
45s	BAS4005W	SIEM	shd×2	V _R <40B; I _F <120mA; V _F (I _F =15mA)<1.0B; I _R <1.0mkA; C _D <5.0nΦ	SOT323,SC70	-
45s	BAS40-05W	INF	shd×2	V _B <40 B; I _E <120 mA; V _E (I _E =40 mA)<1 B; I _B <1.0 mκA; C _D <5 πΦ	SOT323.SC70	
46	BAS4006	VISH	shd×2	V _R <40B; I _E <200 mA; V _E (I _E =40 mA)<1.0B; I _R <0.2 mkA; C _B <5.0 nΦ; t _{BR} <5 HC	SOT23.SOD23	
46	PDTA114TEF	PHIL	Dono	V _{C80} =50 B; I _C =100 MA; P _D =200 MBr; h ₂₁ >200; R ₁ 10 KOM	SOT490.SC89	
46o	BAS4006	PHIL	shd×2	V _B <40 B; I _E <120 mA; V _E (I _E =1 mA)<380 mB; C ₀ <5 nΦ	SOT23,SOD23	
46s	BAS4006	SIEM	shd×2	V _R <40B; I _F <120мA; V _E (I _E =40мA)<1.0B; I _R <1.0мкA; C _D <5.0пФ	SOT23,SOD23	
46s	BAS40-06	INF	shd×2	V _R <40B; I _F <120 mA; V _F (I _F =40 mA)<1B; I _R <1.0 mκA; C _D <5πΦ	SOT23,SOD23	





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
16s	BAS4006W	SIEM	shd×2	V _R <40B; I _F <120 mA; V _F (I _F =15 mA)<1.0 B; I _R <1.0 mκA; C _D <5.0 nΦ	S0T323,SC70	K1 · K2 · A1, A2
16s	BAS40-06W	INF	shd×2	V _B <40B; I _E <120 мА; V _E (I _E =40 мА)<1B; I _B <1.0 мкА; С _п <5 пФ	SOT323,SC70	K1-K2-A1,A2
17	PDTC114YK	PHIL	Dnpn	V _{сво} =50 B; I _с =100 мА; P _о =200 мВт; h ₂₁ >100; 10 кОм/47 кОм	SOT346,SC59	B·E·C
47p	PMBFJ113	PHIL	nFET	V _{DS} =40B; I _{DSS} >2 MA; P _D =300 MBT; R _{DS(on)} <100 OM	SOT23,SOD23	D·S·G
47t	PMBFJ113	PHIL	nFET	V _{DS} =40B; I _{DSS} >2 MA; P _D =300 MBT; R _{DSIgnt} <100 OM	SOT23,SOD23	D-S-G
47V	PZM47NB	PHIL	dz	V ₂ (I ₂₇ =2 mA)=44.050.0 B; Z ₂₇ (I ₂₇ =2 mA) < 90 Om	SOT346,SC59	A·n.c.·K
47W	PMBFJ113	PHIL	nFET	V _{DS} =40B; I _{DSS} >2 мА; Р _D =300 мВт; R _{DS(ort)} <100 Ом	SOT23, SOD23	D·S·G
47X	02CZ47	TOSH	dz	V ₂ (I ₇₇ =2 mA)=44.0049.00 B; I₁(V _R =36B)<0.5 mkA	SOT346,SC59	A·n.c.·K
489	FMMT489	ZETEX	non	V _{GB0} =50 B; I _C = 1000 мА; P _D =500 мВт; h ₂₁ =100300; f _T >150 МГц	SOT23.SOD23	
480	PMBFJ308	PHIL	nFET	V _{DS} =25B; I _{DSS} =1260 MA; P _D =250 MBT; Q _E >10 MCM	SOT23.SOD23	S·D·G
48t	PMBFJ308	PHIL	nFET	V _{DS} =25B; I _{DSS} =1260 мА; Р _D =250 мВт; Q _E >10 мСм	SOT23,SOD23	S·D·G
48W	PMBFJ308	PHIL	nFET	V _{DS} =25B; I _{DSS} =1260 мА; Р _D =250 мВт; g _E >10 мСм	SOT23.SOD23	S·D·G
491	FMMT491	ZETEX	non	V _{CB0} =80 B; I _C =1000 мА; P ₀ =500 мВт; h ₂₁ =100300; f _T >150 МГц	SOT23.SOD23	B-E-C
493	FMMT493	ZETEX	non	V _{GB0} =120 B; I _C =1000 мА; P _D =500 мВт; h ₂₁ =100300; f _T >150 МГц	SOT23.SOD23	B-E-C
494	FMMT494	ZETEX	non	V _{CR0} =140 B; I _C =1000 mA; P _D =500 mBT; h ₂₁ =100300; f _T >100 MFu	SOT23.SOD23	C C C
495	FMMT495	ZETEX	non	V _{CR0} =170B; I _C =1000 MA; P _D =500 MBT; h ₂₁ =100300; f _T >100 MFu	SOT23,SOD23	
497	FMMT497	ZETEX	non	V _{CB0} =300 B; I _C =500 MA; P _D =500 MBr; h ₂₁ =80300; f _T >75 MFu	SOT23.SOD23	
490	PMBFJ309	PHIL	nFET	V _{DS} =25B; I _{DSS} =1230 mA; P _D =250 mBT; Q _E >10 mCm	SOT23.SOD23	
49t	PMBFJ309	PHIL	nFET	V _{DS} =25B; I _{DSS} =1230 MA; P _D =250 MBT; Q _E >10 MCM	SOT23.SOD23	
49W	PMBFJ309	PHIL	nFET	V _{DS} =25B; I _{DSS} =1230 mA; P _D =250 mBT; Q _F > 10 mCm	SOT23.SOD23	2012 20
4A	BC859A	CDIL	pnp	V _{CB0} =30B; I _C =100мA; P ₀ =310мBт; h ₂₁ =110220; f _T >150МГц	SOT23,SOD23	122.22
4A	BC859AW	PHIL	onp	V _{CB0} =30 B; I _C =100 MA; P _D =200 MBT; h ₂₁ =125250; f _T >100 MFu,	S0T323.SC70	
4A	FMMV109	ZETEX	bd	V _R <30B; C _{3.B} =2632 πΦ; C3B/C _{25.B} =56.5; Q>250	SOT23,SOD23	
4A	MMBV109	ZETEX	var	V _R >30B; I _F =200 MA; C _{3B} =2632 nΦ; C _{3B} /C _{25B} =5.06.5	SOT23,SOD23	
4A3	PZM4.3NB2A	PHIL	dz×2	V _X (I ₇₇ =5 MA)=4.154.34 B; Z ₇₇ (I ₇₇ =5 MA)< 90 Om	S0T346,SC59	100000000000000000000000000000000000000
4A7	PZM4.7NB2A	PHIL	dz×2	V _X (I ₇₇ =5 mA)=4.554.75 B; Z ₂₇ (I ₂₇ =5 mA) < 80 Om	SOT346.SC59	
4Ao	BC859A	PHIL	pnp	V _{CBD} =30 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =125250; f _T >100 MFu	SOT23,SOD23	
4AR	BC859AR	PHIL	pnp	V _{CB0} *30 B; I _C *100 mA; P _D *200 mBr; h ₂₁ *125250, f ₇ >150 MΓμ	SOT23,SOD23	
4As	BC859A	SIEM	prip	V _{сва} -30B; I _с =100мA; Р _п =200мBт; I ₂₁ =250; I ₇ >130мПц	SOT23,SOD23	
4As	BC859AW	INF	onp	V _{CRO} =30 B; I _C =100 MA; P _D =350 MBT; N ₂₁ =125250; F _T =250 MFL	SOT323,SC70	
4At	BC859A	PHIL	prip	V _{CB0} =30B; I _C =100MA; P _D =250MB1; h ₂₁ =125250; f _T >100MΓц	SOT23,SOD23	
4B	BC859B	CDIL	prip	V _{CBO} -30B; I _C =100 MA; P _D =230 MB1; I ₁₂₁ =123250; I _T > 100 MI I _Q V _{CBO} =30B; I _C =100 MA; P _D =330 MB1; I _{D21} =220475; I _T > 300 MI I _Q	SOT23,SOD23	1.020.0201.007
4B	BC859B	TOSH	1000	V _{CR0} =30B; I _C =100MA; P _D =330MB1; I ₁₂₁ =220473; I _T =300MΓц V _{CR0} =30B; I _C =100MA; P _D =150MB1; I ₂₁ =220475; I _T =300MΓц	S0T23,S0D23	
4B	BC859B	ZETEX	pnp		SOT23,SOD23	0.000
4B	BC859B	ITT	pnp	V _{CBO} =30 B; I _C =100мA; P _D =330мBr; h ₂₁ =220475; f _T >300МГц		
4B-	BC859BW	PHIL	pnp	V _{CB0} =30 B; I _C =100мA; P _D =330мBт; I ₂₁ =220475; f _T >300МГц	SOT23,SOD23	
-			pnp	V _{CB0} =30 B, I _C =100 мА; P _D =200 мВт; h ₂₁ =220475; f _T >100 МГц	S0T323,SC70	100000000000000000000000000000000000000
4Bp	BC859B	PHIL	pnp	V _{CB0} =30 B; I _C =100 мА; Р _D =250 мВт; h ₂₁ =220475; f _T >100 МГц	SOT23,SOD23	100.000.000
4BR	BC859BR	PHIL	pnp	V _{CB0} =30 B; I _C =100 мA; P _D =200 мВт; h ₂₁ =475; f _T >150 МГц	SOT23,SOD23	
4Bs	BC859B	INF	pnp	V _{CB0} =30 B; I _C =100мA; P _D =330мBr; h ₂₁ =220475; f ₁ =250МГц	SOT23,SOD23	
4Bs	BC859BW	SIEM	pnp	V _{CB0} =30 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =220475; f _T =250 MFц	S0T323,SC70	
4Bt	BC859B	PHIL	pnp	V _{CB0} =30 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =220475; f _T >100 MFц	SOT23,SOD23	
4Bt	BC859BW	PHIL	pnp	V _{CB0} =30 B, I _C =100 мА; Р _D =200 мВт; h ₂₁ =220475; f _T >100 МГц	SOT323,SC70	
4C	BC859C	Ш	pnp	V _{CB0} =30 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =220475; f _T =250 МГц	SOT23,SOD23	
4C	BC859C	CDIL	pnp	V_{CB0} =30 B; I_C =100 MA; P_D =330 MBT; h_{21} =420800; f_T >250 M Γ_{IJ}	S0T23,S0D23	100.00301001
4C	BC859C	TOSH	pnp	V _{CB0} =30 B; I _C =100 мА; P _D =150 мВт; h ₂₁ =420800; f _T =300 МГц	SOT23,SOD23	
4C	BC859C	Ш	pnp	V _{CB0} =30 B; I _C =100 мA; P _D =330 мВт; h ₂₁ =420800; f _T >300 МГц	SOT23,SOD23	16.786.99
4C	FMMV3102	ZETEX	bd	V _R <30B; C _{3B} =2025 πΦ; C3B/C _{25B} >4.5; Q>300	SOT23,SOD23	
1C	MMVB3102	MOT	var	Ст=635пФ	SOT23,SOD23	
4C-	BC859CW	PHIL	pnp	V _{CB0} =30 B; I _C = 100 мА; P _D =200 мВт; h ₂₁ =420800; f _T > 100 МГц	SOT323,SC70	
4Cp	BC859C	PHIL	pnip	V_{CB0} =30B; I_C =100mA; P_D =250mBT; h_{21} =420800; f_T >100M Γ_{II}	SOT23,SOD23	-
4CR	BC859CR	PHIL	pnp	V_{CB0} =30 B; I_C =100 mA; P_D =200 mBr; h_{21} =800; f_T >150 M Γ_{II}	SOT23,SOD23	1.000.00.000
4Cs	BC859C	INF	pnp	V _{CR0} =30 B; I _C =100 mA; P _D =330 mBT; h ₂₁ =420800; f _T =250 MFu,	SOT23,SOD23	B·E·C

Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3
4Cs	BC859CW	INF	pnp	V _{CB0} =30B; I _C =100 mA; P _D =250 mBr; h ₂₁ =420800; f _T =250 MFu	SOT323,SC70	B·E·C
1Ct	BC859C	PHIL	pnp	V _{CR0} =30 B; I _C =100 мA; P ₀ =250 мВт; h ₂₁ =420800; f _T >100 МГц	SOT23,SOD23	B-E-C
1Ct	BC859CW	PHIL	pnp	V ₀₈₀ =30 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =420800; f _T >100 МГц	SOT323,SC70	B-E-C
1D	BC859	CDIL	ono	V _{CR0} =30 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =125800; f _T >100 MFu	SOT23,SOD23	
ID.	HD3A	ZETEX	fid	V _R <75B; I _E <100 mA; V _E (I _E =10 mA)<1.0B; I _R <1.0 mκA; C _D <4.0 nΦ; t _{RR} <6hc		
1D	MMBV3401LT1	ON	oin	V _{BB} >35B; I _B <0.1 мкА; С ₇ <1 пФ	SOT23.SOD23	
1D-	BC859W	PHIL	onp	V _{GR0} =30 B; I _G =100 mA; P _D =200 mBr; h ₂₁ =125800; f _T >100 MFu	SOT323,SC70	
1Do	BC859	PHIL	onp	V _{CB0} =30 B; I _C =100 mA; P _D =250 mBT; h ₂₁ =125800; f _T >100 MFu	SOT23,SOD23	
IDt .	BC859W	PHIL	pnp	V _{CB0} =30 B; I _C =100 MA; P _D =200 MBr; h ₂₁ =125800; f _T >100 MFu	SOT323.SC70	
IE.	BC860A	CDIL	pnp	V _{CB0} =50 B; I _C =100 MA; P _D =250 MBr; h ₂₁ =125250; f _T >100 MF _U	SOT23,SOD23	
IE .	BC860AW	PHIL	pnp	V _{CBB} =50 B; I _C =100 MA; P _D =200 MBT; h ₂₁ =125250; f _T >100 MFu	SOT323,SC70	
IE	FMMTA92	ZETEX	ono	V _{CBO} =300 B; I _C =100 мА; P _D =200 мВт; P _D =125250, YZ 100 мПц	SOT23.SOD23	17.000.000.000
	BC860A	PHIL	1	000	SOT23,30D23	
#Ep	DOM: 00 (0.04.0)	PHIL	pnp	V _{C80} =50 B; I _C =100 мА; P ₀ =250 мВт; h ₂₁ =125250; f _T >100 МГц		Mico 27 (192)
IER	BC860AR		pnp	V _{CB0} =45B; I _C =100 mA; P _D =200 mBr; h ₂₁ =250; f _T >150 MFu	SOT23,SOD23	2000
Et	BC860A	PHIL	pnp	V _{CB0} -50 B; I _C =100 мA; P _D =250 мBτ; h ₂₁ =125250; f _T >100 MΓц	SOT23,SOD23	
IEZ.	FMMV105G	ZETEX	bd	V _R <30B; C _{25B} =1.82.8 nΦ; C3B/C _{25B} =46; Q>350	SOT23,SOD23	
IF .	BC860B	CDIL	pnp	V _{CB0} =50 B; I _C =100 мA; P _D =330 мBr; h ₂₁ =220475; f _T >300 МГц	SOT23,SOD23	
IF .	BC860B	ZETEX	pnp	V _{CB0} =50 B; I _C =100 мA; P _D =330 мВт; h ₂₁ =220475; f _T >300 МГц	SOT23,SOD23	T00570070
IF-	BC860BW	PHIL	pnp	V_{CB0} =50 B; I_C =100 MA; P_D =200 MBT; h_{21} =220475; f_T >100 MFц	SOT323,SC70	1107 11 100
IF p	BC860B	PHIL	pnp	V_{CB0} =50 B; I_C =100 mA; P_D =250 mBr; h_{21} =220475; f_T >100 M Γ_{LL}	SOT23,SOD23	
IFR	BC860BR	PHIL	pnp	V_{CB0} =45 B; I_C =100 mA; P_0 =200 mBr; h_{21} =475; f_T >150 M Γ_{LL}	SOT23,SOD23	
Fs	BC860B	INF	pnp	V_{OB0} =50 B; I_C =100 mA; P_D =330 mBT; h_{21} =220475; f_T =250 M Γ_{II}	SOT23,SOD23	B.E.C
IFs	BC860BW	INF	pnp	V _{CB0} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =220475; f _T =250 МГц	SOT323,SC70	B·E·C
lFt .	BC860B	PHIL	pnp	V _{CB0} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =220475; f _T >100 МГц	SOT23,SOD23	B-E-C
IFt .	BC860BW	PHIL	pnp	V _{CB0} =50 B; I _C =100 мA; P _D =200 мВт; h ₂₁ =220475; f _T >100 МГц	SOT323,SC70	B-E-C
IG	BC860C	CDIL	pnp	V _{DB0} =50 B; I _C =100 мA; P ₀ =250 мВт; h ₂₁ =420800; f _T >100 МГц	SOT23,SOD23	B-E-C
IG	FMMT2484	ZETEX	npn	V _{CBB} =60 B; I _C =50 mA; P _B =330 mBT; h ₂₁ =100500	SOT23,SOD23	B·E·C
IG-	BC860CW	PHIL	ono	V _{GB0} =50 B; I _G =100 мА; P _D =200 мВт; h ₂₁ =420800; f _T >100 МГц	SOT323,SC70	B·E·C
IG ₀	BC860C	PHIL	pnp	V _{CR0} =50 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =420800; f _T >100 MFu	SOT23,SOD23	B·E·C
IGR	BC860CR	PHIL	pnp	V _{CR0} =45B; I _C =100 MA; P _D =200 MBT; h ₂₁ =800; f _T >150 MFu	SOT23.SOD23	
lGs	BC850CW	INF	npn	V _{C80} =50B; I _C =100 mA; P _D =250 mBr; h ₂₁ =420800; f _T =250 MFц	SOT323,SC70	B·E·C
IGs	BC860C	INF	onp	V _{CB0} =50 B; I _C =100 mA; P _D =330 mBT; h ₂₁ =420800; f _T =250 MFц	SOT23,SOD23	
IGs	BC860CW	INF	onp	V _{CRO} =50 B; I _C =100 MA; P _D =250 MBr; h ₂₁ =420800; f _T =250 MFu	SOT323,SC70	
lGt	BC860C	PHIL	pnp	V _{CRO} =50B; I _C =100 MA; P _D =250 MBr; h ₂₁ =420800; f _T >100 MFu	SOT23.SOD23	
lGt	BC860CW	PHIL	pnp	V _{csn} =50 B; I _C =100 MA; P _D =200 MBT; h ₂₁ =420800; f _T >100 MFц	SOT323,SC70	
IGZ	BC860C	ZETEX	one	V ₀₈₀ =50 B; I _C =100 мA; P _D =200 мB; H ₂₁ =420800; f _T >300 МГц	SOT23.SOD23	
H H	BC860	CDIL			SOT23,SOD23	
H H			pnp	V _{C80} =50 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =125800; f _T >100 MFu		
	MMBV2103LT1	MOT	var	V _R >30 B; I _F =200 μA; C _{4 B} =911πΦ; C _{2 B} /C _{30 B} =2.53.2	SOT23,SOD23	100000000000000000000000000000000000000
H-	BC860W	PHIL	pnp	V _{G80} =50 B; I _C =100 мА; P ₀ =200 мВг; h ₂₁ =125800; f ₁ >100 МГц	SOT323,SC70	
Нр	BC860	PHIL	pnp	V _{C80} -50 B; I _C = 100 MA; P _D =250 MBT; h ₂₁ =125800; f _T > 100 MFL	SOT23,SOD23	
Ht	BC860	PHIL	pnp	V_{C80} =50 B; I_C =100 mA; P_D =250 mBT; h_{21} =125800; f_T >100 M Γ_{LL}	SOT23,SOD23	
Ht	BC860W	PHIL	pnp	V_{C80} =50 B; I_C =100 mA; P_D =200 mBr; h_{21} =125800; f_T >100 M Γ_{LI}	SOT323,SC70	
J	FMMT38A	ZETEX	npn	V _{CB0} =80 B; I _C =300 мA; P _D =330 мВт; h ₂₁ >500	SOT23,SOD23	
IJ	MMBV2109LT1	MOT	var	V _R >30 B; I _F =200 мA; C _{4 B} =29.736.3 nФ; C _{2 B} /C _{30 B} =2.53.2	SOT23,SOD23	
М	MMBD101	MOT	shd	$V_R < 4B$; $V_R (I_F = 10 \text{ mA}) < 0.6B$; $I_R < 0.25 \text{ mkA}$; $C_D < 1 \text{ n}\Phi$	SOT23,SOD23	
Ms	BAT240A	INF	shd×2	V _R <240 B; I _F <400 мА; V _F (I _F =50 мА)<470 мВ; С ₀ =11.5пФ	SOT23,SOD23	
IP	FMMT2907R	ZETEX	pnp	V_{C80} =60 B; I_C =600 mA; P_D =330 mBr; h_{21} =100300; f_T >200 M Γ_{LL}	SOT23,SOD23	B-E-C
R	MMBV3700LT1	ON	pin	V _{BR} >200В; I _R <0.1 мкА; С _Т <1 пФ	SOT23,SOD23	A·n.c.·K
Т	MMBD301LT1	ON	shd	V _B >30 B; V _E (I _E =10 мA)<0.6 B; С _T <1.5 пФ	SOT23,SOD23	A·n.c.·K
U	MMBV2105LT1	MOT	var	V _B >30 B; I _F =200 MA; C _{4 B} =13.516.5 nt0; C _{2 B} /C _{30 B} =2.53.2	SOT23,SOD23	A·n.c.·K
V	BCW65AR	ZETEX	npn	V _{CB0} =60 B; I _C =800 мA; P _D =330 мBr; h ₂₁ =100250; f _T >100 MFu	SOT23,SOD23	B-E-C
V	MMBV2106LT1	MOT	var	V _B >30 B; I _E =200 мA; C _{2 B} /C _{30B} =2.53.2	SOT23,SOD23	





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
4V3	PZM4.3NB	PHIL	dz	V _Z (I _{ZT} =5 MA)=4.014.48 B; Z _{ZT} (I _{ZT} =5 MA) < 90 OM	SOT346,SC59	A·n.c.·K
4V7	PZM4.7NB	PHIL	dz	V ₂ (I ₂₇ =5 mA)=4.424.90 B; Z ₂₇ (I ₂₇ =5 mA) < 80 Om	SOT346,SC59	A·n.c.·K
4W	BCW67AR	ZETEX	pnp	V _{CB0} =45B; I _C =800 мA; P _D =330 мВт; h ₂₁ =100250; f _T >100МГц	SOT23,SOD23	B·E·C
4W	MMBV2107LT1	MOT	var	V _B >30B; I _E =200 MA; C _{4B} =19.824.2 пФ; C _{2B} /C _{30B} =2.53.2	SOT23,SOD23	A+n.c.+K
4X	MMBV2108LT1	МОТ	var	V _B >30B; I _F =200 мA; С _{4 B} =24.329.7 пФ; С _{2 B} /С _{30 B} =2.53.2	SOT23,SOD23	A+n.c.+K
4Y	MMBV2102LT1	мот	var	V _B >30B; C ₇ =8.2пФ; C _{2B} /C _{30B} =2.53.2	SOT23,SOD23	A·n.c.·K
4Z	MMBV2104LT1	МОТ	var	V _B >30B; I _E =200 MA; C _{2B} /C _{30B} =2.53.2	SOT23,SOD23	A+n.c.+K
5.1X	02CZ5.1	TOSH	dz	V ₂ (I ₇₇ =5 mA)=4.805.40 B; I ₁ (V _B =1.5B)<1 mkA; Z ₇₇ (I ₇₇ =0.5 mA)<1000 Om	SOT346,SC59	A+n.c.+K
5.6X	02CZ5.6	TOSH	dz	V _Z (I _{ZT} =5 MA)=5.306.00 B; I _L (V _B =2.5B) < 1 MKA; Z _{ZT} (I _{ZT} =0.5 MA) < 900 OM	SOT346,SC59	A·n.c.·K
50	PDTA143EEF	PHIL	Dono	V _{CBD} =50 B; I _C = 100 mA; P _D =250 mB1; h _{P1} > 30; 4.7 kOm/4.7 kOm	SOT490,SC89	B·E·C
50p	PMBFJ310	PHIL	nFET	Vns=25B; Inss=2460 mA; Pn=250 mBT; Qc>10 mCm	SOT23,SOD23	S-D-G
50t	PMBFJ310	PHIL	nFET	V _{DS} =25B; I _{DSS} =2460 мА; Р _D =250 мВт; g _E >10 мСм	SOT23,SOD23	S-D-G
50W	PMBFJ310	PHIL	nFET	V _{DS} =25B; I _{DSS} =2460 мА; Р _D =250 мВт; Q _E >10 мСм	SOT23.SOD23	
51	PDTC143EEF	PHIL	Dnon	V _{CBD} =50B; I _C =100mA; P _D =250mBT; h _{D1} >30; 4.7 kOm/4.7 kOm	SOT490,SC89	B-E-C
517	FMMT6517	ZETEX	non	V _{CR0} =350 B; I _C =500 MA; P _D =330 MBT; h _{P1} =30200; f _T >50 MFц	SOT23.SOD23	
51V	PZM51NB	PHIL	dz	V _Z (I _{ZT} =2 mA)=48.054.0 B; Z _{ZZ} (I _{ZT} =2 mA) < 110 Om	SOT346,SC59	
52	DTA123YE	ROHM	Dono	V _{CRD} =50 B; I _C =100 mA; P _D =150 mBr; h ₂₁ >33; f ₁ >250 MFu;	SOT416.SC75A	
-			- 10.40	R ₁ /R ₂ =2.2/10 kOM		
52	DTA123YKA	ROHM	Dpnp	V_{CB0} =50 B, $I_{\rm G}$ =100 MA; $P_{\rm D}$ =200 MBT; h_{21} >33; $f_{\rm T}$ >250 MFu; $R_{\rm L}/R_{\rm D}$ =2.2/10 kOM	SOT346,SC59	B-E-C
52	DTA123YUA	ROHM	Dpnp	V_{CB0} =50 B, I_C =500 MA; P_D =200 MBT; h_{21} >56; f_T >250 MF χ ; R_1/R_2 =2.2/10 KOM	S0T323,SC70	B•E•C
52	PDTA143ZEF	PHIL	Dpnp	V _{CB0} =50 B; I _C =100 mA; P _D =250 mBr; h ₂₁ > 100; 4.7 кОм/47 кОм	SOT490,SC89	B·E·C
520	FMMT6520	ZETEX	pnp	V_{C80} =350 B; I_C =500 MA; P_0 =330 MBr; h_{21} =30200; f_T >50 M Γ_{II}	SOT23,SOD23	B·E·C
53	BAT17	SIEM	shd	$V_R < 4B$; $I_E < 30$ mA; $V_E (I_E = 10$ mA) $< 0.6B$; $I_R < 0.25$ mKA; $C_0 < 1$ n Φ	SOT23,SOD23	A+n.c.+K
53	BAT17W	SIEM	shd	V _R <4B; I _F <130 mA; V _F (I _F =10 mA)<0.6B; I _R <0.25 mrA; C _D <0.75 πΦ	SOT323,SC70	A·n.c.·K
53	PDTC143ZEF	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 mA; P _D =250 mBr; h ₂₁ > 100; 4.7 кОм/47 кОм	SOT490,SC89	B·E·C
53s	BAT17	INF	shd	V _B <4B; I _F <130 mA; V _F (I _F =1 mA)<450 mB; C _D <1 mΦ	SOT23,SOD23	A+n.c.+C
53s	BAT17W	INF	shd	$V_R < 4B$; $I_F < 130 \text{ mA}$; $V_F (I_F = 10 \text{ mA}) < 0.6B$; $I_R < 0.25 \text{ mkA}$; $C_D < 0.75 \text{ m}$	SOT323,SC70	A+n.c.+K
54	BAT1704	SIEM	shd×2	$V_R \le 4B$; $I_F \le 130 \text{ mA}$; $V_F (I_F = 10 \text{ mA}) \le 0.6B$; $I_R \le 0.25 \text{ mkA}$; $C_D \le 1 \text{ m}$	SOT23,SOD23	A1-K2-K1,A2
54	BAT1704W	SIEM	shd×2	V _R <4B; I _F <130 мA; V _F (I _F =10 мA)<0.6B; I _R <0.25 мкA; C _D <0.75 пФ	SOT323,SC70	A1-K2-K1,A2
54	DTA114YE	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =150 mBt; h_{21} >68; f_T >250 MFu; R_1/R_2 =10/47 кОм	SOT416,SC75A	B-E-C
54	DTA114YKA	ROHM	Dpnp	V_{CB0} =50 B; I_0 =100 MA; P_0 =200 MBT; h_{21} >68; f_1 >250 MFu; R_1/R_2 =10/4.7 KOM	SOT346,SC59	B-E-C
54	DTA114YUA	ROHM	Dpnp	V_{CB0} =50 B; I_C = 100 mA; P_D =200 mBt; h_{21} >68; f_T >250 MFu; R_1/R_2 =10/47 кОм	SOT323,SC70	B·E·C
54	PDTA114YK	PHIL	Dpnp	V _{CB0} =50 B; I _C =100 мA; P _D =200 мВт; h ₂₁ > 100; 10 кОм/47 кОм	SOT346,SC59	B·E·C
54	PDTC143XEF	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ >50; 4.7 кОм/10 кОм	SOT490,SC89	B·E·C
549	FMMT549	ZETEX	pnp	V _{CB0} =35B; I _C =1000 мA; P ₀ =500 мВт; h ₂₁ =100300; f _T >100 МГц	SOT23,SOD23	B·E·C
54s	BAT17-04	INF	shd×2	$V_R < 4B$; $I_F < 130 \text{ mA}$; $V_F (I_F = 1 \text{ mA}) < 450 \text{ mB}$; $C_D < 1 \text{ m}$	SOT23,SOD23	A1.K2.K1,A2
54s	BAT17-04W	INF	shd×2	$V_R \le 4B$; $I_F \le 130 \text{ mA}$; $V_F (I_F = 10 \text{ mA}) \le 0.6B$; $I_R \le 0.25 \text{ mkA}$; $C_D \le 0.75 \text{ m}$	SOT323,SC70	A1 · K2 · K1,A2
55	BAT1705	SIEM	shd×2	$V_R \le 4B$; $I_F \le 130 \text{ mA}$; $V_F (I_F = 10 \text{ mA}) \le 0.6B$; $I_R \le 0.25 \text{ mxA}$; $C_D \le 1 \text{ m}\Phi$	SOT23,SOD23	A1-A2-K1,K2
55	BAT1705W	SIEM	shd×2	$V_R \le 4B$; $I_F \le 130$ mA; $V_F (I_F = 10$ mA) ≤ 0.6 B; $I_R \le 0.25$ mxA; $C_D \le 0.75$ m Φ	SOT323,SC70	A1-A2-K1,K2
551	FMMT551	ZETEX	pnp	V_{C80} =80 B; I_C =1000 MA; P_0 =500 MBr; h_{21} =50150; f_T >150 M Γ_{II}	SOT23,SOD23	B·E·C
555	FMMT555	ZETEX	pnp	V _{CB0} =160 B; I _C =1000 mA; P _D =500 mBT; h ₂₁ =50300; f _T >100 MFu	SOT23,SOD23	B·E·C
558	FMMT558	ZETEX	pnp	V_{C80} =400 B; I_C = 150 mA; P_0 =500 mBt; h_{21} =100300; f_T >50 M Γ_{II}	SOT23,SOD23	B·E·C
55s	BAT17-05	INF	shd×2	V _B <4B; I _F <130 мA; V _F (I _F =1 мA) <450 мB; С ₀ <1 пФ	SOT23,SOD23	A1+A2+K1,K2
55s	BAT17-05W	INF	shd×2	$V_R \le 4B$; $I_F \le 130 \text{ mA}$; $V_F (I_F = 1 \text{ mA}) \le 450 \text{ mB}$; $C_D \le 1 \text{ n}\Phi$	SOT323,SC70	A1-A2-K1,K2
56	BAT1706	SIEM	shd×2	$V_R \le 4B$; $I_F \le 130$ mA; $V_F (I_F = 10$ mA) $\le 0.6B$; $I_R \le 0.25$ mkA; $C_D \le 1$ n Φ	SOT23,SOD23	K1-K2-A1,A2
56	BAT1706W	SIEM	shd×2	$V_R \le 4B$; $I_F \le 130$ mA; $V_F (I_{F^2} = 10$ mA) ≤ 0.6 B; $I_R \le 0.25$ mKA; $C_D \le 0.75$ n Φ	SOT323,SC70	K1-K2-A1,A2
56s	BAT17-06	INF	shd×2	$V_R \le 4B$; $I_F \le 130$ mA; $V_F (I_F = 10$ mA) ≤ 0.6 B; $I_R \le 0.25$ mKA; $C_D \le 1$ n Φ	SOT23,SOD23	K1 · K2 · A1,A2
56s	BAT17-06W	SIEM	shd×2	$V_R \le 4B$; $I_E \le 130$ mA; $V_E (I_E = 10$ mA) ≤ 0.6 B; $I_R \le 0.25$ mKA; $C_D \le 0.75$ m Φ	SOT323,SC70	K1-K2-A1,A2
56V	PZM56NB	PHIL	dz	V _Z (I _{ZT} =2 mA)=52.060.0 B; Z _{ZT} (I _{ZT} =2 mA) < 120 Om	SOT346,SC59	A+n.c.+K
576	FMMT576	ZETEX	pnp	V _{CB0} =200 B; I _C =1000 mA; P _D =500 mBt; h ₂₁ =50300; f _T >100 MFu	SOT23,SOD23	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
589	FMMT589	ZETEX	pnp	V_{CB0} =50 B; I_C =1000 mA; P_D =500 mBt; h_{21} =100300; f_T >100 MFu	SOT23,SOD23	B-E-C
59	DTA114YE	MOT	Dpnp	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 150 \text{ mBT}; h_{21} > 68; f_T > 250 \text{ MFu}; R_1/R_2 = 10/47 \text{ kOm}$	SOT416,SC75A	B·E·C
591	FMMT591	ZETEX	pnp	V ₀₈₀ *80 B; I _C = 1000 мА; P _D =500 мВт; h ₂₁ = 100300; f _T >150 МГц	SOT23,SOD23	B-E-C
593	FMMT593	ZETEX	pnp	V _{G80} =120B; I _C =1000 мА; P _D =500 мВт; h ₂₁ =100300; f ₇ >50 МГц	SOT23,SOD23	B-E-C
596	FMMT596	ZETEX	pnp	V_{C80} = 220 B; I_C = 300 mA; P_D =500 mBT; h_{21} = 85300; f_T > 150 MFL	SOT23,SOD23	B-E-C
597	FMMT597	ZETEX	pnp	V_{C80} =300 B; I_C =200 mA; P_D =500 mBT; h_{21} =100300; f_T >75 MFu	SOT23,SOD23	B-E-C
59A	FMMT549A	ZETEX	pnp	V _{сво} =35 B; I _C =1000 мА; P _C =500 мВт; h ₂₁ =150500; f _T >100 МГц	SOT23,SOD23	B·E·C
5A	BC807-16	CDIL	pnp	V _{сво} =45 B; I _с =500 мА; P _D =250 мВт; h ₂₁ =100250; f _T >80 МГц	SOT23,SOD23	B-E-C
5A	BC807-16LT1	MOT	pnp	V _{DB0} =50 B; I _C =500 мA; P _D =300 мВт; h ₂₁ =100250; f _T > 200 МГц	SOT23,SOD23	B-E-C
5A	BC807-16W	PHIL	pnp	V ₀₈₀ =50 B; I _C =500 мА; P _D =200 мВт; h ₂₁ =100250; f _T >80 МГц	SOT323,SC70	B-E-C
5A	BSS123	MOT	nMOS	V _{DS} = 100 B; I _D = 170 мА; P _D = 330 мВт; g _E = 90 мСм; R _{DSign1} = 14 0 м	SOT23,SOD23	G-S-D
5A	FMMD6050	ZETEX	fid	V_R <70.B; I_F <200 мA; V_F (I_F =100 мA)<1.1 B; I_R <0.1 мкA; C_D <2.5 п Φ ; I_{BR} <5 н C	SOT23,SOD23	A·n.c.·K
5A	MMBD6050LT1	MOT	di	$V_B > 70 \text{ B}; I_E < 200 \text{ mA}; V_E (I_E = 100 \text{ mA}) < 1.1 \text{ B}; C_D < 2.5 \text{ m}\Phi; t_{BB} < 4 \text{ Hc}$	SOT23,SOD23	A·n.c.·K
5A1	PZM5.1NB2A	PHIL	dz×2	V ₂ (I _{ZT} =5 mA)=4.985.20 B; Z _{ZT} (I _{ZT} =5 mA)<60 Om	SOT346,SC59	K1-K2-A1,A2
5A6	MMBZ5V6AL	ON	dz×2	V ₂ (I _{ZT} =1 MA)=5.325.88 B; V _E (I _E =10 MA)<0.9 B	SOT23,SOD23	K1-K2-A1,A2
5A6	PZM5.6NB2A	PHIL	dz×2	V _Z (I _{ZT} =5 mA)=5.495.73 B; Z _{ZT} (I _{ZT} =5 mA)<40 Om	SOT346,SC59	K1-K2-A1,A2
5Ар	BC807-16	PHIL	pnp	V ₀₈₀ =45 B; I _C =500 мА; P _D =250 мВт; h ₂₁ =100250; f _T >80 МГц	SOT23,SOD23	B·E·C
5AR	BC807-16R	PHIL	pnp	V _{ово} =50 B; I _о =500 мА; P _о =250 мВт; h ₂₁ >250; f ₇ >100 МГц	SOT23,SOD23	E-B-C
5As	BC807-16	SIEM	pnp	V ₀₈₀ =50 B; I _C =500 мА; P _D =330 мВт; h ₂₁ =100250; f _T =200 МГц	SOT23,SOD23	B-E-C
5As	BC807-16W	SIEM	pnp	V _{сво} =50 B; I _C =500 мА; P _D =250 мВт; h ₂₁ =100250; f _T =200 МГц	SOT323,SC70	B-E-C
5AZ	BC807-16	ZETEX	pnp	V ₀₈₀ =50 B; I _C =500 мА; P _D =330 мВт; h ₂₁ =100250; f _T >100 МГц	SOT23,SOD23	B·E·C
5B	BC80725	CDIL	pnp	V ₀₈₀ =45B; I _C =500 мА; P _D =250 мВт; h ₂₁ =160400; f _T >80 МГц	SOT23,SOD23	B·E·C
5B	BC807-25	STM	pnp	V _{G80} =50 B; I _C =500 мA; P _D =250 мВт; h ₂₁ =160400; f _T >80 МГц	SOT23,SOD23	B-E-C
5B	BC80725LT1	MOT	ono	V _{G80} =50 B; I _C =500 мA; P _D =300 мВт; h ₂₁ =160400; f _T >200 МГц	SOT23,SOD23	B-E-C
5B	BC80725W	PHIL	pnp	V ₀₈₀ =50 B; I _C =500 мA; P _D =200 мВт; h ₂₁ =160400; f _T >80 МГц	SOT323,SC70	B-E-C
5B	FMMD6100	ZETEX	fid×2	V_R <70B; I_F <200 MA; V_F (I_F =100 MA)<1.1 B; I_R <0.1 MKA; C_D <2.5 n Φ ; I_{BR} <5 HC	SOT23,SOD23	A1+A2+K1,K2
5B	KST4123	SAMS	npn	V _{DB0} =40 B; I _C =200 мА; P _D =350 мВт; h ₂₁ =50150; f _T >250 МГц	SOT23,SOD23	B-E-C
5B	MMBT4123	SAMS	npn	V _{гвп} =40 B; I _с =200 мА; Р _п =350 мВт; h ₂₁ =50150	SOT23,SOD23	B-E-C
5B	MMBT4123	MOT	ngn	V _{G80} =40 B; I _C =200 mA; P _D =350 mBr; h ₂₁ =50150	SOT23,SOD23	B-E-C
5BM	MMBD6100LT1	MOT	di×2	V _B >70 B; I _E <200 mA; V _E (I _E =100 mA)<1.1 B; C _D <2.5 nΦ; t _{BB} <4 HC	SOT23.SOD23	A1-A2-K1.K2
5Bo	BC80725	PHIL	ono	V _{CBB} =45B; I _C =500 мA; P _D =250 мВт; h ₂₁ =160400; f _T >80 МГц	SOT23.SOD23	B-E-C
5Bs	BC80725	SIEM	ono	V _{DBD} =50 B; I _C =500 мA; P _D =330 мВт; h _{Pl} =160400; f _T =200 МГц	SOT23,SOD23	B-E-C
5Bs	BC80725W	SIEM	onp	V _{CRO} =50 B; I _C =500 MA; P _D =250 MBT; h ₂₁ =160400; f _T =200 MFu	SOT323,SC70	-
5Bt	BC80725	PHIL	pnp	V _{can} =45B; I _c =500 мA; P _n =250 мВт; h ₂₁ =160400; f _T >80 МГц	SOT23,SOD23	1974/03 174
5BZ	BC80725	ZETEX	ono	V _{CB0} =50 B; I _C =500 мA; P _D =330 мВт; h ₂₁ =160400; f _T > 100 МГц	SOT23.SOD23	B-E-C
5C	BAT54CLT1	ON	shd×2	V _B <30 B; I _E <200 mA; V _E (I _E =30 mA)<500 mB; I _{BB} <5 HC	SOT23,SOD23	A1-A2-K1.K2
5C	BC807-40	CDIL	ono	V _{GB0} =50 B; I _C =500 mA; P _D =330 mBt; h ₂₁ =250630; f _T >200 MFu	SOT23,SOD23	-
5C	BC807-40	STM	pnp	V _{CR0} =50 B; I _C =500 мA; P _D =250 мВт; h ₂₁ =250600; f _T > 100 МГц	SOT23,SOD23	
5C	BC80740LT1	MOT	ono	V _{CB0} =50 B; I _C =500 mA; P _D =300 mBT; h ₂₁ =250600; f _T >200 MFц	SOT23.SOD23	
5C	BC807-40W	PHIL	ono	V _{C80} =50 B; I _C =500 mA; P _D =200 mBT; h ₂₁ =250600; f _T >80 MFц	-	B-E-C
5C	FMMD7000	ZETEX	fid×2	$V_R < 70B$; $I_F < 200$ mA; $V_F (I_F = 100$ mA) < 1.1 B; $I_R < 0.3$ mKA; $C_D < 2.5$ n Φ ; $I_{SR} < 15$ Hz	SOT23,SOD23	
5Co	BC807-40	PHIL	pnp	V _{C80} =45 B; I _C =500 мA; P _D =250 мВт; h ₂₁ =250600; f _T >80 МГц	SOT23,SOD23	B-E-C
5CR	BC807-40R	PHIL	ono	V _{CB0} =50B; I _C =500 MA; P _D =310 MBr; h ₂₁ >600; f _T >100 MFu	SOT23,SOD23	-
5Cs	BC807-40	SIEM	pnp	V _{G80} =50 B; I _G =500 mA; P _D =330 mBr; h ₂₁ =250630; f _T =200 MFu	SOT23,SOD23	
5Cs	BC807-40W	INF	ono	V _{GR0} =50 B; I _C =500 MA; P _D =250 MBr; h ₂₁ =250630; f _T =200 MFu	SOT323.SC70	
5CZ	BC807-40	ZETEX	ono	V _{CBO} =50 B; I _C =500 MA; P _D =330 MBr; h ₂₁ =250600; f _T >100 MFц	SOT23,SOD23	
5D	BC807	CDIL	ono	V _{C80} =45 B; I _C =500 MA; P _D =250 MBr; h ₂₁ =100600; f _T >80 MΓ _U	SOT23,SOD23	222
5D	BC807W	PHIL	prip	V _{CB0} =50 B; I _C =500 MA; P _D =200 MB; h ₂₁ =100600; f _T >80 MFu	SOT323,SC70	100000000000000000000000000000000000000
5D	DAN212N3	CYS	di	V _R <70B; I _F <200 MA; P _D <250 MB; V _F (I _F : 150 MA)<1.25 B; t _{RF} <4 HC	SOT23,SOD23	





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
5D	FMMD914	ZETEX	fid	$V_R < 75B$; $I_F < 225$ mA; $V_F (I_F = 10$ mA} < 1.0 B; $I_R < 0.025$ mKA; $C_D < 4.0$ n Φ ; $I_{BR} < 8$ HC.	SOT23,SOD23	A•n.c.•K
5D	HD2A	ZETEX	fid×2	V _B <35B; I _F <100 mA; V _F (I _F =10 mA)<1.0B; I _B <1.0 mkA; C _D <4.0 nΦ; t _{BB} <6 HC	SOT23,SOD23	A1+A2+K1,K2
5D	MMBD914LT1	MOT	di	V _B >100 B; I _E <200 mA; V _E (I _E =10 mA) <1B; C _D <4 nΦ; t _{RB} <4 hc	SOT23,SOD23	A+n.c.+K
5D	TMPD4148	ALLEG	d	I _E <600 mA; V _{BR} > 100 B; V _F (I _F =10 mA) < 1.0 B; I _R < 25 πA; t _{PR} < 4.0 πC; Co < 4.0 πΦ	SOT23,SOD23	A•n.c.•K
5D	TMPD914	ALLEG	d	I_F < 600 mA; V_{BR} > 100 B; V_F (I_F = 10 mA) < 1.0 B; I_R < 25 nA; I_{BR} < 4.0 nc; C_0 < 6.0 n Φ	SOT23,SOD23	A•n.c.•K
5Dp	BC807	PHIL	pnp	V _{CB0} =45 B; I _C =500 мА; P ₀ =250 мВт; h ₂₁ =100600; f _T >80 МГц	SOT23,SOD23	B·E·C
5DZ	BC807	ZETEX	pnp	V _{CB0} =50B; I _C =500мA; P _D =330мBт; h ₂₁ =100600; f _T =100МГц	SOT23,SOD23	B·E·C
SE I	BC808-16	CDIL	pnp	V _{CB0} =30 B; I _C =500 мA; P _D =330 мВт; h ₂₁ =100250; f _T > 100 МГц	SOT23,SOD23	B·E·C
5E	BC808-16W	PHIL	pnp	V _{CB0} =25B; I _C =500 mA; P _D =200 mBT; h ₂₁ =100250; f _T >80 MFu	SOT323,SC70	B·E·C
5E	FMMTA43R	ZETEX	non	V _{CR0} =200 B; I _C =200 мА; P ₀ =330 мВт; h ₂₁ =50200; f _T >50 МГц	SOT23, SOD23	B·E·C
5Eo	BC808-16	PHIL	pnp	V _{CB0} =25B; I _C =500 мA; P _D =250 мВт; h ₂₁ =100250; f _T >80 МГц	SOT23,SOD23	B-E-C
5ER	BC808-16R	PHIL	ono	V _{CR0} =30 B; I _C =500 mA; P _D =310 mBT; h ₂₁ > 250; f _T >100 MFu,	SOT23.SOD23	E·B·C
5Es	BC808-16	SIEM	onp	V _{CR0} =30 B; I _C =500 mA; P _D =330 mBτ; h ₂₁ =100250; f _T =200 MΓu	SOT23.SOD23	B·E·C
	BC808-16W	INF	onp	V _{CB0} =30 B; I _C =500 mA; P _D =250 mBr; I _{D1} =100250; f _T =200 MFu	SOT323,SC70	125/211/22
	BC808-16	PHIL	pnp	V _{CR0} =25B; I _C =500мA; P _D =250мBт; h ₂₁ =100250; f _T >80МГц	SOT23,SOD23	
	BC808-16	ZETEX	pnp	V _{CR0} =30 B; I _C =500 мА; P _D =330 мВт; h ₂₁ =100250; f _T >100 МГц	SOT23.SOD23	
	BC808-25	CDIL	prip	V _{CBD} =30 B; I _C =500 мА; P _D =330 мВт; h ₂₁ =160400; f _T > 200 МГц	SOT23,50D23	
	BC808-25W	PHIL	ono	V _{CR0} =25 B; I _C =500 MA; P _D =200 MBT; h _{Cl} =160400; f _T >80 MFu	SOT323,SC70	
	BC808-25W	PHIL	onp	V _{CR0} =25B; I _C =500 MA; P _D =250 MBT; I _{D2} =160400; f _T >80 MFu	SOT23.SOD23	
	BC808-25R	PHIL				200000000000000000000000000000000000000
			pnp	V _{CB0} =30 B; I _C =500 MA, P _D =310 MBτ; h ₂₁ >400; f _T >100 MΓц	SOT23,SOD23	
	BC808-25	SIEM	pnp	V _{CB0} =30 B; I _C =500 MA; P _D =330 MBT; h ₂₁ =160400; f ₁ =200 MF _U	SOT23,SOD23	
	BC808-25W	INF	pnp	V _{CB0} =30 B; I _C =500 mA; P _D =250 mBT; h ₂₁ =160400; f _T =200 MFu	SOT323,SC70	
	BC80825	ZETEX	pnp	V _{CB0} =30 B; I _C =500 мA; P _D =330 мВт; h ₂₁ =160 400; f _T > 100 МГц	SOT23,SOD23	
	BC808-40	CDIL	pnp	V _{CB0} =30 B; I _C =500 мA; P _D =330 мBт; h ₂₁ =250630; f _T >200 МГц	SOT23,SOD23	
	BC808-40W	PHIL	pnp	V _{CB0} =25B; I _C =500 мА; P _D =200 мВт; h ₂₁ =250600; f _T >80 МГц	SOT323,SC70	23//22/17/
or order	BC808-40	PHIL	pnp	V _{CB0} =25B; I _C =500 мА; P _D =250 мВт; h ₂₁ =250600; f _T >80 МГц	SOT23,SOD23	
	BC808-40R	PHIL	pnp	V_{CB0} =30 B; I_C =500 mA; P_D =310 mBr; h_{21} >100; f_T >100 M Γ_{II}	SOT23,SOD23	T-12
	BC808-40	SIEM	pnp	V _{CB0} =30 B; I _C =500 мА; P _D =330 мВт; h ₂₁ =250630; f _T =200 МГц	SOT23,SOD23	100000000000000000000000000000000000000
0.00	BC808-40W	INF	pnp	V _{CB0} =30 B; I _C =500 мА; P _D =250 мВт; h ₂₁ =250630; f _T =200 МГц	SOT323,SC70	
5Gt	BC808-40	PHIL	pnp	V_{CB0} =25B; I_C =500 mA; P_D =250 mBT; h_{21} =250600; f_T >80 MFu	SOT23,SOD23	B-E-C
	BC808-40	ZETEX	pnp	V_{CB0} =30 B; I_C =500 mA; P_D =330 mBT; h_{21} =250600; f_T >100 MF μ	SOT23,SOD23	B·E·C
5H	BC808	CDIL	pnp	V _{CB0} =25 B; I _C =500 мА; P _D =250 мВт; h ₂₁ =100600; f _T >80 МГц	SOT23,SOD23	B·E·C
5H	BC808W	PHIL	pnp	V _{CB0} =25B; I _C =500 мA; P _D =200 мВт; h ₂₁ =100600; f _T >80 МГц	SOT323,SC70	B·E·C
5H	MMBD4148	VISH	di	$V_R < 75B$; $I_F < 300 \text{ mA}$; $V_E (I_F = 10 \text{ mA}) < 1.0 B$; $I_R < 5.0 \text{ m/A}$; $C_D < 4 \text{ n}\Phi$; $I_{ER} < 6 \text{ hc}$	SOT23,SOD23	A·n.c.·K
5H	MMBD4148	NS	di	$V_R < 75B$; $I_F < 300$ mA; $V_F (I_{F^2} = 10$ mA) < 1.0 B; $I_R < 5.0$ mxA; $C_D < 4$ n Φ ; $t_{RR} < 6$ HC	SOT23,SOD23	A+n.c.+K
5H	MMBD701LT1	MOT	shd	V _R >70B; V _E (I _E =10mA)<1B; C _D <1 mΦ	SOT23,SOD23	A·n.c.·K
5Hp	BC808	PHIL	pnp	V _{CR0} =25B; I _C =500 MA; P _D =250 MBT; h ₂₁ =100600; f _T >80 MFu	SOT23,SOD23	B·E·C
5HZ	BC808	ZETEX	pnp	V _{GB0} =30 B; I _G =500 mA; P _D =330 mBT; h ₂₁ =100600; f _T >100 MFц	SOT23,SOD23	B·E·C
5J	FMMT38B	ZETEX	non	V _{CB0} =80 B; I _C =300 mA; P _D =330 mBT; h ₂₁ >2000	SOT23,SOD23	B-E-C
5K	MMBV809LT1	ON	var	V _B >20 B; I _E =20 мA; C _{2 B} =4.56.1 пФ; C _{2 B} /C _{8 B} =1.82.6	SOT23.SOD23	A·n.c.·K
	MMBV609LT1	ON	var×2	V _B >20B; I _F =100мA; С _{3B} =2632пФ; С _{3B} /С _{BB} =1.82.4	SOT23,SOD23	100000000000000000000000000000000000000
	MMBD452LT1	MOT	shd×2	V _R >30B; V _r (I _F =10 _M A)<0.45B; C _T <1.5nΦ	SOT23.SOD23	
	FMMT2907AR	ZETEX	ono	V _{CR0} =60 B; I _C =600 мА; P _D =330 мВт; h _D =100300; f _T >200 МГц	SOT23,SOD23	
	BCW66GR	ZETEX	non	V _{CR0} =75B; I _C =800 MA; P _D =330 MBT; h ₂₁ =160400; f _T >100 MFц	SOT23,SOD23	
	BCW66GR	SIEM	non	V _{CBD} =75B; I _C =800 MA; P _D =330 MB; N ₂₁ =160400; f _T =170 MFц	SOT23,30D23	
	BCW68GR	ZETEX	one	V _{CBD} =60 B; I _C =800 мA; P _D =330 мBт; h _D =160400; f _T >100 МГц	SOT23,50D23	100000000000000000000000000000000000000
3033	BCW65BR	ZETEX	non	V _{CB0} =60 B; I _C =800 мA; P _D =330 мВт; N ₂₁ =160400; f _T >100 МГц	SOT23,50D23	1.5000000000
	PZM5.1NB	PHIL	dz	V _{CB0} =60 B; I _C =600 MA; P _D =330 MB1; II ₂₁ =160400; I _T >100 MI I _L V _X II _{ZT} =5 MA)=4.845.37 B; Z _{ZY} II _{ZT} =5 MA) < 60 Om	SOT346.SC59	T0077-1-70
			_	2000		
5V6	PZM5.6NB	PHIL	dz	V _Z (I _{ZT} =5 mA)=5.315.92 B; Z _{Z1} (I _{ZT} =5 mA) < 40 Om	SOT346,SC59	A·n.c.·K

SOT490 TESM VMT3 1 3 SOT523 SOT323 SOT23-3 1 3 SOT523 SOT323 SOT3

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
W	BCW67BR	ZETEX	pnp	V _{G80} =45B; I _C =800 MA; P _D =330 MBT; h ₂₁ =160400; f _T >100 MFu	SOT23,SOD23	B-E-C
3.2X	02CZ6.2	TOSH	dz	V ₂ (I ₂₇ =5 mÅ)=5.806.60 B; I ₁ (V _B =3.0 B)<1 mkÅ; Z ₂₇ (I ₂₇ =0.5 mÅ)<500 Om	SOT346,SC59	A·n.c.·K
3.8	DF3A6.8FU	TOSH	oz×2	V ₂ (I ₂₇ =5 mA)=6.47.2 B; I ₈ (V _P =5.0 B)<0.5 mrA	SOT323,SC70	K1-K2-A1,A2
6.8X	02CZ6.8	TOSH	dz	V ₂ (I _{ZT} =5 mA)=6.407.20 B; I ₁ (V _B =5.0B)<0.5 mkA; Z _{ZT} (I _{ZT} =0.5 mA)<150 Om	SOT346,SC59	A·n.c.·K
614	FMMT614	ZETEX	npn	V _{CB0} =120 B; I _C =500 mA; P _D =500 mBT; h ₂₁ >15000	SOT23,SOD23	B-E-C
617	FMMT617	ZETEX	npn	V _{C80} =15B; I _C =3000 MA; P _D =625 MBT	SOT23,SOD23	B·E·C
618	FMMT618	ZETEX	npn	V _{CR0} =20 B; I _C =2500 мА; P _D =625 мВт; h ₂₁ =300450; f _T >140 МГц	SOT23,SOD23	B·E·C
619	FMMT619	ZETEX	npn	V _{CR0} =50 B; I _C =2000 мА; P _D =625 мВт; h ₂₁ =300450; f _T >160 МГц	SOT23,SOD23	B-E-C
61A	MMBF4117	FAIR	nFET	V _{DS} =40 B; I _{SE} =50 mA; P _D =225 mBr; Q _E =3 mC	SOT23.SOD23	
61C	MMBF4118	FAIR	nFET	V _{DS} =40 B; I _{SE} =50 MA; P _D =225 MBT; Q _E =5 MC	SOT23,SOD23	D·S·G
61E	MMBF4119	FAIR	nFET	Vng =40 B; lg= 50 mA; Pn=225 mBT; g= 10 mc	SOT23,SOD23	
61J	MMBF4091	FAIR	nFET	V _{DS} =40 B; I _{SF} = 50 мА; P _D =350 мВт; R _{DS(on)} <30 Ом	SOT23.SOD23	200000
61K	MMBF4092	FAIR	nFET	V _{DS} =40 B; I _{SF} =50 мA; P _D =350 мВт; R _{DS(on)} < 50 Ом	SOT23.SOD23	S-D-G
61L	MMBF4093	FAIR	nFET	V _{DS} =40 B; I _{SF} = 50 mA; P _D = 350 mBr; R _{DS/cm} < 80 Om	SOT23,SOD23	
61S	MMBF5458	FAIR	nFET	V _{DS} = 25 B; I _{GF} = 10 mA; P _D = 350 mBr; I _{DSS} < 9 mA	SOT23,SOD23	7000000 -000
615	MMBFJ270	FAIR	oFET	Vns = 30 B; Iss = 50 mA; Pn = 225 mBT; Inss < 15 mA	SOT23.SOD23	
61T	MMBF5459	NS	nFET	V _{DS} = 25 B; I _{SF} = 10 MA; P _D = 350 MBr; I _{DSS} < 16 MA	SOT23,SOD23	
61U	MMBF5461	FAIR	oFET	V _{DS} =40 B; I _{SF} = 10 MA; P _D =300 MBT; I _{DSS} <9 MA	SOT23,SOD23	2,000,000
61V	MMBF5462	FAIR	oFET	V _{DS} =40 B; I _{SF} = 10 MA; P _D =300 MBT; I _{DSS} < 16 MA	SOT23,SOD23	100000 900
62	DTC123YE	ROHM	Dnpn	V _{CB0} =50 B; I _C =100 мA; P _D =150 мBт; h ₂₁ >33; f _T >250 MFu; R _T /R _D =2.2/10 κOM	SOT416,SC75A	7.00 0
62	DTC123YKA	ROHM	Dnpn	V_{C80} =50 B; I_C = 100 MA; P_0 = 200 MB τ ; h_{21} >33; f_T > 250 MF u ; R_T/R_0 = 2.2/10 KOM	SOT346,SC59	B-E-C
62	DTC123YUA	ROHM	Dnpn	V_{CB0} =50 B; I_c = 100 xA; P_0 = 200 xBr; h_{21} > 33; f_T > 250 MFu; R_T/R_2 = 2.2/10 xOx	SOT323,SC70	B-E-C
624	FMMT624	ZETEX	npn	V _{CB0} =125B; I _C =1000 мА; P _D =625 мВт; h ₂₁ =300450; f ₇ >155 МГц	SOT23,SOD23	B·E·C
625	FMMT625	ZETEX	npn	V _{CB0} =150 B; I _C =1000 мA; P _D =625 мВт; h ₂₁ =300450; f _T >135 МГц	SOT23,SOD23	B·E·C
62P	MMBFJ201	FAIR	nFET	V _{DS} =40 B; I _{SF} =50 мА; P _D =350 мВт; I _{DSS} <1 мА	SOT23,SOD23	S·D·G
62Q	MMBFJ202	FAIR	nFET	V _{DS} =40 B; I _{GF} = 50 MA; P _D = 350 MBT; I _{DSS} < 4.5 MA	SOT23,SOD23	S-D-G
62T	MMBFJ271	FAIR	pFET	V _{DS} = 30 B; I _{SF} = 50 MA; P _D = 225 MBT; I _{DSS} < 50 MA	SOT23,SOD23	D·S·G
62V	PZM62NB	PHIL	dz	V ₂ (I ₂₇ =2 mA)=58.066.0 B; Z ₂₇ (I ₂₇ =2 mA)<140 Om	SOT346,SC59	A·n.c.·K
63	BAS40W	PHIL	shd	V _B <40B; I _E <120mA; V _E (I _E =1 mA)<380mB; C _D <5 nΦ	SOT323,SC70	A·n.c.·K
63Q	MMBFJ304	NS	nFET	V _{DS} =30 B; I _{SF} =50 MA; P _D =350 MBT	SOT23,SOD23	D·S·G
63s	BAT64	INF	shd	V _B <40 B; I _E <250 mA; V _E (I _E =100 mA)<0.75 B; I _B <2 mkA; C _D <6 nΦ	SOT23,SOD23	A·n.c.·K
63s	BAT64W	INF	shd	V _B <40 B; I _E <250 mA; V _E (I _E =100 mA)<0.75 B; I _B <2 mkA; C _D <6 nΦ	SOT323,SC70	A1·n.c.·K
64	BAS4004W	PHIL	shd×2	V _B <40 B; I _E <120 mA; V _E (I _E =1 mA)<380 mB; C _D <5 πΦ	SOT323,SC70	A1-K2-K1,A2
64	DTC114YE	ROHM	Dnpn	V_{CB0} =50B; I_C =100 MA; P_D =150 MBT; h_{21} >68; f_T >250 MFu; R_1/R_2 =10/47 KOM	SOT416,SC75A	B-E-C
64	DTC114YKA	ROHM	Dnpn	$V_{CR0}=50 B; I_C=100 \text{ mA}; P_D=200 \text{ mBT}; h_{21}>68; f_T>250 MFu; R_1/R_2=10/47 \text{ kOm}$	SOT346,SC59	B·E·C
64	DTC114YUA	ROHM	Dnpn	V _{GR0} =50 B; I _G =100 MA; P _D =200 MBT; h ₂₁ >68; F _T >250 MFu; P ₁ /R ₂ =10/47 KOM	SOT323,SC70	B·E·C
64s	BAT6404	SIEM	shd×2	V _B <40 B; I _E <250 mA; V _E (I _E =100 mA)<0.75 B; I _B <2 mkA; C _B <6 nΦ	SOT23,SOD23	A1-K2-K1,A2
64s	BAT64-04	INF	shd×2	V _R <40 B; I _F <250 mA; V _F (I _F =100 mA)<0.75 B; I _R <2 mkA; C _D <6 nΦ	SOT23,SOD23	A1-K2-K1,A2
64s	BAT64-04W	INF	shd×2	V _B <40 B; I _E <250 мA; V _E (I _E =100 мA)<0.75 B; I _B <2 мкA; С _D <6 пФ	SOT323,SC70	A1-K2-K1,A2
65	BAS4005W	PHIL	shd×2	V _B <40 B; I _E <120 mA; V _E (I _E =1 mA)<380 mB; C _D <5 πΦ	SOT323,SC70	A1+A2+K1,K2
65s	BAT6405	SIEM	shd×2	V _B <40 B; I _E <250 мA; V _E (I _E =100 мA)<0.75 B; I _B <2 мкA; С _D <6 пФ	SOT23,SOD23	A1-A2-K1,K2
65s	BAT64-05	INF	shd×2	V _R <40 B; I _F <250 mA; V _F (I _F =100 mA)<0.75 B; I _R <2 mkA; C _D <6 nΦ	SOT23,SOD23	A1-A2-K1.K2
65s	BAT64-05W	INF	shd×2	V _B <40 B; I _E <250 мA; V _E (I _E =100 мA)<0.75 B; I _B <2 мкA; С _D <6 пФ	SOT323,SC70	
66	BAS4006W	PHIL	shd×2	V ₀ < 40 B; I ₀ < 120 mA; V ₀ (I ₀ = 1 mA) < 380 mB; C ₁ < 5 nΦ	SOT323,SC70	
66s	BAT6406	SIEM	shd×2	V _R <40 B; I _F <250 мA; V _F (I _F =100 мA) < 0.75 B; I _R <2 мкА; С _П <6 пФ	SOT23,SOD23	
36s	BAT64-06	INF	shd×2	V _R <40 B; I _ε <250 mA; V _ε (I _ε =100 mA)<0.75 B; I _R <2 mkA; C _D <6 nΦ	SOT23,SOD23	
66s	BAT64-06W	INF	shd×2	V _R <40 B; I _c <250 mA; V _c (I _c =100 mA)<0.75 B; I _R <2 mkA; C _D <6 nΦ	SOT323.SC70	
68V	PZM68NB	PHIL	dz	V _Z (I _{ZT} =2 MA)=64.072.0 B; Z _{ZT} (I _{ZT} =2 MA)<160 OM		A·n.c.·K
69	DTC114YE	MOT	Dnpn	V _{CB0} =50 B; I _C =100 mA; P _D =150 mBT; h ₂₁ >68; f _T >250 MFu; R ₁ /R ₂ =10/47 κOm		





Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3
69	DTC115TE	ROHM	Dnpn	V _{CB0} =50 B; I _C =100 mA; P _D =150 mBT; h ₂₁ =100600; f _T >250 MFU; R ₁ =100 kOm	SOT416,SC75A	B-E-C
6A	BC817-16	CDIL	npn	V _{CB0} =50 B; I _C =500 мА; P _D =330 мВт; h ₂₁ =100250; f _T >170 МГц	SOT23,SOD23	B·E·C
6A	BC817-16	VISH	npn	V _{CB0} =50 B; I _C =800 мА; P ₀ =310 мВт; h ₂₁ =100250; f _T >100 МГц	SOT23,SOD23	B·E·C
6A	BC817-16LT1	MOT	npn	V _{CB0} =50 B; I _C =500 мА; P _D =300 мВт; h ₂₁ =100250; f _T >200 МГц	SOT23,SOD23	B·E·C
6A	BC817-16W	PHIL	npn	V _{CB0} =50 B; I _C =500 мA; P _D =200 мВт; h ₂₁ =100250; f _T > 100 МГц	SOT323,SC70	B·E·C
6A	DTA114EET1	MOT	Dpnp	V_{CB0} =50B; I_C =100 mA; P_D =150 mBt; h_{21} >30; f_T >250 MFu; R_1/R_2 =10/10 кОм	SOT416,SC75A	B·E·C
6A	MMBF4416	MOT	nFET	V _{DS} =30B; I _G <10 мA; P _D =300 мВт; NF<4дБ	SOT23,SOD23	D·S·G
6A	MUN2111T1	ON	Dpnp	V _{CBO} =50 B; I _C =100 mA; P _D =246 mBT; h ₂₁ > 35; 10 kOm/10 kOm	SOT346,SC59	B·E·C
6A	MUN5111T1	ON	Dpnp	V _{C80} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ > 35; 10 kOm/10 kOm	SOT323,SC70	B·E·C
6A2	MMBZ6V2AL	ON	dz×2	V _Z (I _{ZT} =1 mA)=5.896.51 B; V _E (I _E =10 mA) < 0.9 B	SOT23,SOD23	K1-K2-A1,A2
6A2	PZM6.2NB2A	PHIL	dz×2	V _Z (I _{Z1} =5 mA)=6.066.33 B; Z _{Z1} (I _{Z1} =5 mA) < 10 Om	SOT346,SC59	K1 · K2 · A1,A2
6A8	MMBZ6V8AL	ON	dz×2	V _z (I _{zz} =1 mA)=6.467.14 B; V _z (I _z =10 mA)<0.9 B	SOT23,SOD23	K1-K2-A1,A2
6A8	PZM6.8NB2A	PHIL	dz×2	V ₂ (I ₂₇ =5 mA)=6.656.93 B; Z ₂₇ (I ₂₇ =5 mA) < 15 Om	SOT346,SC59	K1 · K2 · A1 , A2
6Ap	BC817-16	PHIL	npn	V _{CB0} =45B; I _C =500мA; P _D =250мBт; h ₂₁ =100250; f _T >80МГц	SOT23,SOD23	B·E·C
6AR	BC817-16R	PHIL	npn	V _{св0} =45B; I _c =500 мA; P _D =310 мВт; h ₂₁ >250; f _T >200 МГц	SOT23,SOD23	E·B·C
6As	BC817-16	SIEM	npn	V _{CBD} =50B; I _C =500 мA; P _D =330 мВт; h ₂₁ =100250; f _T =170 МГц	SOT23,SOD23	B·E·C
6As	BC817-16W	SIEM	npn	V _{CBD} =50 B; I _C =500 мА; P _D =250 мВт; h ₂₁ =100250; f _T > 170 МГц	SOT323,SC70	B·E·C
6At	BC817-16	PHIL	non	V _{сво} =45 B; I _c =500 мА; P _D =250 мВт; h _O =100250; f _T >80 МГц	SOT23,SOD23	B·E·C
6AZ	BC817-16	ZETEX	npn	V _{CR0} =50B; I _C =500 MA; P _D =330 MBT; h ₂₁ =100250; f _T =200 MFu	SOT23,SOD23	B·E·C
6B	BC817-25	CDIL	npn	V _{CB0} =45B; I _C =500мA; P _D =250мBт; h ₂₁ =160400; f _T >80МГц	SOT23,SOD23	B·E·C
6B	BC817-25	VISH	non	V _{CB0} =50B; I _G =800 мA; P _D =310 мВт; h ₂₁ =160400; f _T >100МГц	SOT23,SOD23	B·E·C
6B	BC817-25LT1	MOT	npn	V _{CBD} =50B; I _C =500мA; P _D =300мBт; h ₂₁ =160400; f _T >200МГц	SOT23,SOD23	B·E·C
6B	BC817-25W	PHIL	non	V _{CBD} =50B; I _C =500 мA; P _D =200 мВт; h ₂₁ =160400; f _T >100 МГц	SOT323,SC70	B-E-C
6B	DTA124EET1	МОТ	Dpnp	V_{CB0} =50 B, $I_{C(max)}$ =100 mA; P_D =150 mBT; h_{21} >56; f_T >250 MFu; P_1/P_2 =22/22 xOm	S0T416,SC75A	B·E·C
6B	MMBF5484	МОТ	nFET	V _{DG} =25B; I _{GE} =10 MA; P _D =200 MBT; I _{DSS} <5 MA	SOT23,SOD23	D·S·G
6B	MUN2112T1	ON	Dpnp	V _{CRO} =50 B; I _C =100 mA; P _D =246 mBT; h ₂₁ >60; 22 kOm/22 kOm	SOT346,SC59	B·E·C
6B	MUN5112T1	ON	Dpnp	V _{CBD} =50B; I _C =100 mA; P _D =200 mBT; h ₂₁ >60; 22 kOm/22 kOm	SOT323,SC70	B·E·C
6BG	CMPF4416A	CSI	nFET	V _{GSS} >35B; I _{DSS} =515мА; V _{GSIoIII} =2.56B; NF=2дВ	SOT23,SOD23	D·S·G
6Вр	BC817-25	PHIL	npn	V _{CBD} =45B; I _C =500мA; P _D =250мBт; h ₂₁ =160400; f _T >80МГц	SOT23,SOD23	B·E·C
6BR	BC817-25R	PHIL	non	V _{CR0} =45B; I _C =500 мА; P _D =310 мВт; h ₂₁ >400; f _T >200 МГц	SOT23,SOD23	E·B·C
6Bs	BC817-25	SIEM	non	V _{сво} =50 B; I _с =500 мA; P _D =330 мВт; h ₂₁ =160400; f ₁ =170 МГц	SOT23,SOD23	B·E·C
6Bs	BC817-25W	INF	non	V _{CBD} =50B; I _C =500мA; P _D =250мBт; h _{D1} =160400; f _T =170МГц	SOT323,SC70	B·E·C
6BZ	BC817-25	ZETEX	npn	V _{сво} =50 B; I _с =500 мА; P _о =330 мВт; h ₂₁ =160400; f _T =200 МГц	SOT23,SOD23	B·E·C
6C	BC817-40	CDIL	npn	V _{CRD} =50B; I _C =500мA; P _D =330мBт; h ₂₁ =250630; f _T >170МГц	SOT23,SOD23	B·E·C
6C	BC817-40	VISH	non	V _{CBD} =50 B; I _C =800 мА; P _D =310 мВт; h ₂₁ =250630; f _T > 100 МГц	SOT23,SOD23	B·E·C
6C	BC817-40LT1	мот	non	V _{CR0} =50 B; I _C =500 mA; P _D =300 mBT; h _{D1} =250600; f _T >200 MFц	SOT23,SOD23	B·E·C
6C	BC817-40W	PHIL	non	V _{CB0} =45B; I _C =500 мA; P _D =200 мВт; h ₂₁ =250600; f _T >100 МГц	SOT323,SC70	B·E·C
6C	DTA144EET1	МОТ	Dpnp	V_{CB0} =50B; $I_{C(max)}$ =100 mA; P_0 =150 mBT; h_{21} >68; f_T >250 MFu; R_1/R_0 =47/47 xOm	SOT416,SC75A	B·E·C
6C	MMBFU310LT1	мот	nFET	V _{DS} =25B; I _{SF} =10mA; P _D =225 mBr; I _{DSS} <60 mA	SOT23.SOD23	D·S·G
6C	MUN2113T1	ON	Dono	V _{CBO} =50B; I _C =100 mA; P _D =246 mBT; h ₂₁ >80; 47 kOm/47 kOm	SOT346.SC59	B·E·C
6C	MUN5113T1	ON	Dono	V _{CRD} =50B; I _C =100 MA; P _D =200 MBT; h ₂₁ >80; 47 KOM/47 KOM	SOT323,SC70	0000000000
6Co	BC817-40	PHIL	non	V _{CB0} =45 B; I _C =500 мА; P _D =250 мВт; h ₂₁ =250600; f _T >80 МГц	SOT23.SOD23	
6CP	BC817-40R	PHIL	non	V _{CB0} =45 B; I _C =500 MA; P _D =310 MBr; h ₂₁ >600; f _T >200 MΓ _{II}	SOT23.SOD23	
6Cs	BC817-40	SIEM	non	V _{CRO} =50 B; I _C =500 MA; P _D =330 MBT; h ₂₁ =250630; f ₇ =170 MFu	SOT23,SOD23	
6Cs	BC817-40W	INF	non	V _{CR0} =50 B; I _C =500 MA; P _D =250 MBT; h ₂₁ =250630; f _T =170 MFц	SOT323.SC70	
6Ct	BC817-40W	PHIL	non	V _{CB0} =45 B; I _C =500 MA; P _D =250 MB; h ₂₁ =250650; f _T >80 MF _U	SOT23,SOD23	
6CZ	BC817-40	ZETEX	non	V _{CB0} =50 B; I _C =500 MA; P _D =330 MB; h ₂₁ =250600; f _T =260 MF _L	SOT23,SOD23	1.50000000
6D	BC817	CDIL	non	V _{CR0} =50 B; I _C =500 MA; P _D =330 MB; h ₂₁ =230600; f _T >200 MFц	SOT23,SOD23	
UU	DTA114YET1	MOT	ubu	V _{CB0} =50 B; I _C =500 MA; P _D =350 MB1; I ₁₂₁ =100500; I _T >200 MΓц; R ₁ /R ₂ =10/47 κOM		

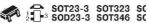
Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3
6D	MMBF5457	FAIR	nFET	V _{DS} =25 B; I _{GF} =10 mA; P _D =350 mBT; I _{DSS} <5 mA	SOT23,SOD23	S-D-G
6D	MUN2114T1	ON	Dpnp	V _{CBO} =50B; I _C =100mA; P _D =246mBr; h ₂₁ >80; 10kOm/47kOm	SOT346,SC59	B-E-C
6D	MUN5114T1	ON	Dpnp	V _{CB0} =50B; I _C =100 MA; P _D =200 MBr; h ₂₁ >80; 10 kOm/47 kOm	SOT323,SC70	B-E-C
6D-	BC817W	PHIL	npn	V _{CB0} =50 B; I _C =500 мA; P _D =200 мВт; h ₂₁ =100600; f _T >100 МГц	SOT323,SC70	B-E-C
6Dp	BC817	PHIL	npn	V _{CB0} =45B; I _C =500 мA; P _D =250 мВт; h ₂₁ =100600; f _T >80 МГц	SOT23,SOD23	B·E·C
6Dt	BC817W	PHIL	npn	V _{G80} =50 B; I _C =500 мA; P _D =200 мВт; h ₂₁ =100600; f _T >100 МГц	SOT323,SC70	B-E-C
6DZ	BC817	ZETEX	npn	V _{сво} =50 B; I _C =500 мА; P _D =330 мВт; h ₂₁ =100600; f _T =200 МГц	SOT23,SOD23	B·E·C
6E	BC818-16	CDIL	npn	V _{GB0} =30 B; I _G =500 MA; P _D =330 MBT; h ₂₁ =100250; f _T > 170 MFц	SOT23,SOD23	B·E·C
6E	BC818-16W	PHIL	npn	V _{CB0} =30 B; I _C =500 мА; P _D =200 мВт; h ₂₁ =100250; f _T >100 МГц	SOT323,SC70	B·E·C
6E	DTA114TET1	MOT	Dono	V _{CB0} =50 B; I _C =100 MA; P _D =150 MBT; h ₂₁ =100600; f _T >250 MFu; R ₁ =10 kOM	SOT416,SC75A	B·E·C
6E	FMMTA93R	ZETEX	pnp	V _{CB0} =200 B; I _C =200 mA; P _D =330 mBr; h ₂₁ =30150; f _T >50 MFu	SOT23,SOD23	B·E·C
6E	MMBF5460	MOT	pFET	V _{DS} =40 B; I _{SF} = 10 MA; P _D =300 MBT; I _{DSS} <5 MA	SOT23,SOD23	D·S·G
6E	MMBF5460	FAIR	pFET	V _{DS} =40 B; I _{SE} = 10 MA; P _D =300 MBT; I _{DSS} <5 MA	SOT23,SOD23	D-S-G
6E	MUN2115T1	ON	Donp	V _{CBO} =50 B; I _C =100 mA; P _D =246 mBT; h ₂₁ > 160; R ₁ 10 kOm	SOT346,SC59	B•E•C
6E	MUN5115T1	ON	Dpnp	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBt; h ₂₁ > 160; R ₁ 10 kOm	SOT323,SC70	B-E-C
6Ep	BC818-16	PHIL	npn	V _{G80} =25B; I _G =500 MA; P _D =250 MBT; h ₂₁ =100250; f _T >80 MFu	SOT23,SOD23	B-E-C
6ER	BC818-16R	PHIL	npn	V _{CB0} =25B; I _C =500 MA; P _D =310 MBr; h ₂₁ =250; f _T >200 MFu	SOT23,SOD23	
6Es	BC818-16	SIEM	npn	V _{CB0} =30 B; I _C =500 MA; P _D =330 MBT; h _{Pl} =100250; f _T =170 MFu	SOT23,SOD23	B-E-C
6Es	BC818-16W	INF	npn	V _{C80} =30 B; I _C =500 mA; P _D =250 mBr; h ₂₁ =100250; f _T =170 MFu	SOT323,SC70	100/100/100
6Et	BC818-16	PHIL	non	V _{CBB} =25B; I _C =500 мA; P _D =250 мВт; h ₂₁ =100250; f _T >80 МГц	SOT23.SOD23	1100 110 100
6EZ	BC818-16	ZETEX	non	V _{CBB} =30 B; I _C =500 мA; P _D =330 мВт; h ₂₁ =100250; f _T >200 МГц	SOT23.SOD23	12227 22
6F	BC818-25	CDIL	npn	V _{C80} =30 B; I _C =500 мA; P _D =330 мBт; h ₂₁ =160400; f _T >170 МГц	SOT23,SOD23	
6F	BC818-25	PHIL	non	V _{G80} =30 B; I _C =500 mA; P _D =330 mBr; h ₂₁ =160400; f _T >200 MFц	SOT23.SOD23	
6F	BC818-25W	PHIL	non	V _{CR0} =30 B; I _C =500 мA; P _D =200 мBт; h ₂₁ =160400; f _T >100 MΓц	SOT323.SC70	
6F	DTA143TET1	MOT	Dpnp	V ₀₈₀ =50 B; I _C =100 MA; P _D =150 MBT; h ₂₁ =100600; f _T >250 MFu; R ₁ =4.7 KOM	SOT416,SC75A	20220
6F	MMBF4860	MOT	nFET	V _{DS} =30 B; I _G <50 mA; P _D =300 mBt	SOT23,SOD23	D-S-G
6F	MUN2116T1	ON	Dono	V _{GBO} =50 B; I _G =100 mA; P _D =246 mBr; h ₂₁ > 160; R ₁ 4.7 kOm	SOT346.SC59	100000000000000000000000000000000000000
6F	MUN5116T1	ON	Dono	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBr; h ₂₁ >160; R ₁ 4.7 κOm	SOT323.SC70	B-E-C
6Fp	BC818-25	PHIL	npn	V _{C80} =25B; I _C =500 MA; P _D =250 MBT; h ₂₁ =160400; f _T >80 MFu	SOT23,SOD23	B-E-C
6FR	BC818-25R	PHIL	npn	V _{CB0} =25B; I _C =500 MA; P _D =310 MBT; h ₂₁ =400; f _T >200 MF _U	SOT23,SOD23	E-B-C
6Fs	BC818-25	INF	npn	V _{GB0} =30 B; I _G =500 мA; P _D =330 мВт; h ₂₁ =160400; f _T =170 МГц	SOT23,SOD23	B-E-C
6Fs	BC818-25W	INF	npn	V _{сво} =30 B; I _c =500 мА; P _D =250 мВт; h ₂₁ =160400; f _T >170 МГц	SOT23,SOD23	B-E-C
6FZ	BC818-25	ZETEX	npn	V _{csn} =30 B; I _c =500 мA; P _n =330 мВт; h ₂₁ =160400; f _T >200 МГц	SOT23,SOD23	B-E-C
6FZ	BC818-25	ZETEX	npn	V _{G80} =30 B; I _G =500 мА; P _D =330 мВт; h ₂₁ =160400; f _T >200 МГц	SOT23,SOD23	B-E-C
6G	BC818-40	CDIL	npn	V ₀₈₀ = 25 B; I _C = 500 мА; P _D = 250 мВт; h ₂₁ = 250600; f _T > 80 МГц	SOT23,SOD23	B-E-C
6G	BC818-40W	PHIL	npn	V _{CR0} =30 B; I _C =500 MA; P _D =200 MBT; h ₂₁ =250600; f _T >100 MFu	SOT323.SC70	B-E-C
6G	CMPF4393	CSI	nFET	V _{GSS} >40 B; I _{DSS} =530 MA; V _{GSInth} =0.53B; R _{DSInth} <100 OM; t _{DFF} <50 Hc	SOT23,SOD23	D·S·G
6G	FMMV2103	ZETEX	bd	V _B <30B; C _{4B} =911πΦ; C _{2B} /C _{30B} =2.63.3; Q>400	SOT23,SOD23	20000
6G	MMBF4393	FAIR	nFET	V _{DS} = 30 B; I _{SF} = 50 мА; P _D = 350 мВт; R _{DS(m)} < 100 Ом	SOT23,SOD23	100000000000000000000000000000000000000
6G	MMBF4393LT1	ON	nFET	V _{DS} =30 B; I _{SF} =50 mA; P _D =350 mBr; R _{DS(on)} < 100 Om	SOT23,SOD23	100000 000
6G	MUN2130T1	ON	Donp	V _{CBO} =50B; I _C =100mA; P _D =246 mBr; h ₂₁ >3; 1 kOm/1 kOm	SOT346.SC59	70.00
6G	MUN5130T1	ON	Dono	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >3; 1 kOm/1 kOm	SOT323,SC70	
6Go	BC818-40	PHIL	npn	V _{CRO} =25 B; I _C =500 мA; P _D =250 мBr; h ₂₁ =250600; f _T >80 MΓц	SOT23,SOD23	
6GR	BC818-40R	PHIL	npn	V _{C80} =25 B; I _C =500 MA; P _D =310 MBr; h ₂₁ =600; f _T >200 MF _U	SOT23,SOD23	
6Gs	BC818-40	INF	npn	V _{CBO} =30 B; I _C =500 MA; P _D =330 MBr; h ₂₁ =250630; f _T > 170 MFu	SOT23,SOD23	300000000000
6Gs	BC818-40W	INF	npn	V _{CBO} =30 B; I _C =500 MA; P _D =250 MBr; h ₂₁ =250630; f _T =170 MFu	SOT323.SC70	0.000.00
6Gt	BC818-40	PHIL	nan	V ₀₈₀ =25 B; I _C =500 mA; F _D =250 mBr; h ₂₁ =250600; f _T >80 MFu	SOT23.SOD23	
6GZ	BC818-40	ZETEX	npn	V _{C80} =30 B; I _C =500 MA; P _D =330 MB; h ₂₁ =250630; f _T >200 MF _U	SOT23,SOD23	
6H	BC818	CDIL	npn	V _{C80} =35 B; I _C =500 мА; P _D =350 мВт; N ₂₁ =250650; f _T >250 мГц	SOT23,SOD23	
	DOGIO	ODIL	119011	ACRO FOR HE GOO WAY LEG. FOR MID! LIST. LOO OON! ILA ON MILT	00120,00020	D L-0





Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3
6H	DTA123EET1	МОТ	Dpnjo	V_{CB0} =50 B, I_C =100 MA; P_D =150 MBT; h_{21} >20; f_T >250 MFu; R_1/R_2 =2 2/2.2 xGM	SOT416,SC75A	B-E-C
6H	FMMV2104	ZETEX	bd	V _B <30B; C _{4B} =10.813.2пФ; C _{2B} /C _{30B} =2.63.3; Q>400	SOT23,SOD23	A·n.c.·K
6H	MMBF5486	MOT	nFET	V _{DS} =25B; I _{SF} =10mA; P _D =300 mBT; I _{DSS} <20 mA	SOT23,SOD23	D·S·G
5H	MUN2131T1	ON	Dono	Vone=50 B; In=100 mA; Pn=246 mBT; hn=>8; 2.2 kOm/2.2 kOm	SOT346,SC59	B·E·C
6H	MUN5131T1	ON	Dono	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >8; 2.2 kOm/2.2 kOm	SOT323,SC70	B·E·C
6Нр	BC818	PHIL	non	V _{CB0} =25B; I _C =500 мА; P _D =250 мВт; h ₂₁ =100600; f _T >80 МГц	SOT23,SOD23	B·E·C
5HZ	BC818	ZETEX	non	V _{CR0} =30 B; I _C =500 mA; P _D =330 mBT; h ₂₁ =100600; f _T >200 MFL	SOT23.SOD23	B·E·C
ŝ.J	CMPF4391	CSI	nFET	V _{GSS} >40 B; I _{DSS} =50150 mA; V _{GSloth} =410 B; R _{DSloth} <30 Om; t _{OFF} <20 HC	SOT23,SOD23	D-S-G
6J	DTA143EET1	МОТ	Dpnp	V_{CB0} =50 B, I_c = 100 mA; P_D =150 mBT; h_{21} >20; $\hat{\tau}_1$ >250 MFu; P_1 /Ro-4.7/4.7 xCm	S0T416,SC75A	B·E·C
ŝJ	FMMV2105	ZETEX	bd	V _B <30 B; C _{4B} =13.516.5 nΦ; C _{2B} /C _{30B} =2.63.3; Q>400	SOT23,SOD23	A·n.c.·K
SJ.	MMBF4391	FAIR	nFET	V _{DG} =30 B; I _{GF} =50 mA; P _D =350 mBT; R _{DS(m1)} <30 Om	SOT23.SOD23	D·S·G
ŝJ	MMBF4391LT1	ON	nFET	V _{DG} =30 B; I _{GE} =50 MA; P _D =350 MBT; R _{DS(cd)} <30 OM	SOT23.SOD23	D-S-G
ŝJ	MUN2132T1	ON	Dono	V _{CBO} =50 B; I _C =100 mA; P _D =246 mB⊤; h ₂₁ >15; 4.7 кОм/4.7 кОм	SOT346.SC59	B·E·C
ŝJ	MUN5132T1	ON	Dpnp	V _{CB0} =50B; I _C =100 mA; P _D =200 mBT; h ₂₁ > 15; 4.7 kOm/4.7 kOm	SOT323.SC70	
3K	CMPF4392	CSI	nFET	V _{GSS} >40B; I _{DSS} =2575MA; V _{GSIatri} =25B; R _{DSIatri} <60OM; t _{DFF} <35Hc	SOT23.SOD23	
5K	DTA143ZET1	MOT	Dpnp	V _{CB0} =50B; I _C =100mA; P _D =150mBT; h ₂₁ >80; f _T >250 MFU; R ₁ /R ₂ -4.7/47;OM	SOT416,SC75A	
5K	MMBF4392	FAIR	nFET	V _{DB} =30 B; I _{BF} =50 mA; P _D =350 mBT; R _{DS(on)} < 60 Om	SOT23 SOD23	D·S·G
5K	MMBF4392LT1	ON	nFET	V _{DG} =30 B; I _{GF} =50 MA; P _D =350 MBT; R _{DS(DG)} <60 OM	SOT23.SOD23	
SK	MUN2133T1	ON	Dpnp	V _{CRO} =50 B; I _C =100 MA; P _D =246 MBT; h ₂₁ >80; 4.7 KOM/47 KOM	SOT346,SC59	
SK	MUN5133T1	ON	Dono	V _{CBD} =50B; I _C =100 MA; P _D =200 MBT; h ₂₁ >80; 4.7 KOM/47 KOM	SOT323,SC70	
SL	DTA124XET1	MOT	Dono	V _{CBD} =50 B; I _C =100 MA; P _D =200 MBT; h ₂₁ >68; f _T >250 MFU; R ₁ /R ₂ =22/47 KOM		
ž šL	FMMV2107	ZETEX	bd	V _B <30B; C _{4B} =19.824.2nΦ; C _{2B} /C _{30B} =2.73.3; Q>350	SOT23.SOD23	-
iL	MMBF5459	FAIR	nFET	V _{ng} =25B; I _{ng} =10mA; P _n =350 mBT; I _{ngs} <16mA	SOT23,SOD23	
л. 31	MUN2134T1	ON	Dono	V _{CBD} =50B; I _C =100 MA; P _D =346 MBT; I _{DSS} < 10 MA V _{CBD} =50B; I _C =100 MA; P _D =246 MBT; I _{DSS} < 22 KOM/47 KOM	SOT346.SC59	
5L	MUN5134T1	ON	Dono	V _{CBO} =50B; I _C =100 MA; P _D =240 MB1; N ₂₁ >80; 22 KOM/47 KOM	SOT323.SC70	
BM	DTA123JET1	MOT	Dpnp	V _{C80} -50 B, I _C -100 IMA, P _D -200 MBT, H ₂₁ >80, 22 κ0M/4.7 κ0M V _{C80} -50 B; I _C -100 IMA; P _D -150 MBT; H ₂₁ >80; f _T >250 MFц; R ₁ /R ₂ -2.2/47 κ0M	SOT416,SC75A	75////
SM S	FMMV2108	ZETEX	hd	V _R <30B; C _{4B} =24.329.7nΦ; C _{2B} /C _{30B} =2.73.3; Q>300	SOT23.SOD23	A-nc-K
5M	MMBF5485	NS	nFET	V _{na} =25B; I _{ns} =10MA; P _n =300 MBT	SOT23,SOD23	100000000000000000000000000000000000000
SM	MUN5135T1	ON	Dono	V _{CR0} =50B; I _G =100mA; P _D =200mBT; h ₂₁ >80; 2.2kOm/4.7 kOm	SOT323.SC70	
6N	DTA115EET1	MOT	Dpnp	V _{CB0} = 50.B; I _{C Cm2} = 100; P ₀ = 150 MBT; h ₂₁ > 82; f ₇ > 250 MFu; R ₁ /R ₂ = 100/100 kOM	SOT416,SC75A	
6N	FMM/2109	ZETEX	bd	V _B <30B; C _{4B} =29.336.3nΦ; C _{2B} /C _{30B} =2.73.3; Q>280	SOT23 SOD23	A-nc-K
6N	MMBF4861	NS	nFET	V _{DS} =30B; P _D =350mBr; R _{DS/ont} <600m	SOT23.SOD23	
SN SN	MUN2136T1	ON	Dono	V _{CRC} =50 B; I _C =100 MA; P _D =246 MBT; h _{Pl} >80; 100 KOM/100 KOM	SOT346.SC59	
SN SN	MUN5136T1	ON	Dono	V _{CBD} =50B; I _C =100 kA; P _D =240 kB; H ₂₁ >80; 100 kOM/100 kOM V _{CBD} =50B; I _C =100 kA; P _D =200 kB; H ₂₁ >80; 100 kOM/100 kOM	SOT323.SC70	
SP.	BCX71HR	ZETEX	ano	V _{CBD} =45B; I _C =200мA; P _D =230мB; h ₂₁ >80, 100 кому 100 ком V _{CBD} =45B; I _C =200мA; P _D =330мB; h ₂₁ =180310; f _T >180МГц	SOT23,SOD23	100000000000000000000000000000000000000
SP	BCX71HR	PHIL	prip	V _{CB0} -45B; I _C -200MA; P _D -330MBT; h ₂₁ -180310; f _T >180MFц	SOT23,SOD23	-
SP	DTA144WET1	MOT	Dpnp	V _{C80} -43-6, f _c -200 MA; P _D -330 MD1, f ₁₂₁ -180310, f ₇ -7180 MTu; V _{C80} -50 B; I _{C(max)} -100 MA; P _D -200 MBT; h ₂₁ >56; f ₇ >250 MTu; R ₁ /R ₂ -47/22 KOM	SOT416,SC75A	
3P	MMBFJ111	FAIR	nFET	V _{DB} =35 B; I _{BF} =50 mA; P _D =225 mBT; R _{DS(on)} < 30 Om	SOT23,SOD23	S·D·G
5P	MUN2137T1	ON	Dono	V _{CRO} =50B; I _C =100 MA; P _D =246 MBT; h ₂₁ >80; 47 KOM/22 KOM	SOT346.SC59	
5P	MUN5137T1	ON	Dono	V _{CB0} =50B; I _C =100 MA; P _D =200 MBT; h ₂₁ >80; 47 KOM/22 KOM	SOT323,SC70	
60	MMBFJ305	NS	nFET	V _{DE} =30 B; I _{DE} =50 MA; P _D =350 MBT	SOT23.SOD23	1000
SR	FMMV2101	ZETEX	bd	V _B <30B; C _{4B} =6.17.5nΦ; C _{2B} /C _{30B} =2.53.3; Q>450	SOT23.SOD23	76337 (2)
SP.	MMBFJ112	FAIR	nFET	V _{DS} =35 B; I _{SF} =50 MA; P _D =225 MBT; R _{DS(DI)} <50 OM	SOT23,SOD23	
an SS	MMBFJ113	FAIR	nFET	V _{DG} =35 B; I _{GF} =50 MA; P _D =225 MBT; R _{DS(o1)} \ 30 OM	SOT23,SOD23	
ST	BCW68GR	SIEM	pnp	V _{CP0} =60 B; I _C =800 MA; P _D =220 MD1; H _{DS} (o ₁) \ 100 CM V _{CP0} =60 B; I _C =800 MA; P _D =330 MB1; h _{D1} =160400; f _T >100 MΓц	SOT23,SOD23	
3T	MMBFJ310	NS	nFET	V _{DG} =25B; I _{GF} =50 MA; P _D =350 MBτ	SOT23,SOD23	
J 1	MUN2140T1	ON	Dono	V _{CBO} =50 B; I _C =100 MA; P _D =300 MBT; h ₂₁ >120; R ₁ 47 KOM	SOT346,SC59	5000 B

Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3
6t3	1PS70SB40	PHIL	shd	V _R <40 B; I _F <120 mA; V _F (I _F =1 mA)<380 mB; C _D <5 nΦ	SOT323,SC70	A·n.c.·K
6t4	1PS70SB44	PHIL	shd×2	$V_R \le 40 \text{ B}; I_F \le 120 \text{ mA}; V_F (I_F = 1 \text{ mA}) \le 380 \text{ mB}; C_D \le 10 \text{ n}\Phi$	SOT323,SC70	A1 · K2 · K1, A2
6t5	1PS70SB45	PHIL	shd×2	$V_B < 40 B$; $I_F < 120 mA$; $V_F (I_F = 1 mA) < 380 mB$; $C_D < 10 m\Phi$	SOT323,SC70	A1+A2+K1,K2
6t6	1PS70SB46	PHIL	shd×2	V _B < 40 B; I _F < 120 mA; V _F (I _F =1 mA) < 380 mB; C _D < 10 πΦ	SOT323,SC70	K1·K2·A1,A2
6U	MMBFJ309	NS	nFET	V _{DS} = 25 B; I _{SF} = 50 mA; P _D = 350 mBt	SOT23,SOD23	D·S·G
6V	BCW65CR	ZETEX	npn	V_{C80} =60 B; I_C =800 mA; P_D =330 mBt; h_{21} =250630; f_T >100 M Γ_{II}	SOT23,SOD23	B·E·C
6V2	PZM6.2NB	PHIL	dz	V ₂ (I _{ZT} =5 mA)=5.866.53 B; Z _{ZT} (I _{ZT} =5 mA) < 10 Om	SOT346,SC59	A·n.c.·K
6V8	PZM6.8NB	PHIL	dz	V _Z (I _{ZT} =5 mA)=6.477.14 B; Z _{ZT} (I _{ZT} =5 mA)<15 Om	SOT346,SC59	A·n.c.·K
6W	BCW67CR	ZETEX	pnp	V_{C80} =45B; I_C =800 mA; P_D =330 mBr; h_{21} =250630; f_T >100 MFu,	SOT23,SOD23	B·E·C
6W	MMBFJ175	FAIR	pFET	V _{DS} =30 B; I _{SF} =50 MA, P _D =225 MBT; R _{DS(on)} < 125 OM	SOT23,SOD23	D·S·G
6X	MMBFJ176	FAIR	pFET	V _{DS} = 30 B; I _{SF} = 50 MA; P _D = 225 MBT; R _{DS/ont} < 250 OM	SOT23,SOD23	D·S·G
6Y	MMBFJ177	FAIR	pFET	V _{DS} =30 B; I _{SF} =50 мА; Р _D =225 мВт; R _{DS(on)} <300 Ом	SOT23,SOD23	D·S·G
6Z	MMBF170LT1	MOT	nMOS	V _{DS} =60 B; I _D =500 mA; P _D = 225 mBT	SOT23,SOD23	G·S·D
7.5X	02CZ7.5	TOSH	dz	V ₂ (I _{2T} =5 mA)=7.007.90 B; I ₁ (V _R =6.0B)<0.5 mKA; Z _{2T} (I _{2T} =0.5 mA)<120 0m	SOT346,SC59	A·n.c.·K
702	2N7002	VISH	nFET	V _{DS} =60 B; I _D =115 мA; P _D =200 мВт; V _{DS} <2.5B; C _{DD} =60 пФ	SOT23,SOD23	G-S-D
702W	L2N7002LT1	LRC	nFET	V _{DS} =60 B; I _D =115 мА; P _D =300 мВт; V _{BSTH} =12.5B; C _{ISS} <50 пФ	SOT23,SOD23	G-S-D
717	FMMT717	ZETEX	ono	V _{CB0} =12B; I _C =2500 MA; P _D =625 MBT	SOT23,SOD23	B·E·C
718	FMMT718	ZETEX	ono	V ₀₈₀ =20 B; I ₀ =1500 мА; P ₀ =625 мВт; h ₂₁ =300450; f _T >180 МГц	SOT23,SOD23	B·E·C
720	FMMT720	ZETEX	ono	V _{свп} =40 B; I _C =1500 мА; P _D =625 мВт; h _{P1} =300450; f _T >190 МГц	SOT23.SOD23	100/10/10/1985
722	FMMT722	ZETEX	ono	V _{C80} =70 B; I _C =1500 мА; P _D =625 мВт; h ₂₁ =300450; f ₁ >200 МГц	SOT23.SOD23	B·E·C
723	FMMT723	ZETEX	ono	V _{CBB} =100 B; I _C =1000 мA; P _D =625 мВт; h _{D1} =300450; f _T >200 МГц	SOT23.SOD23	B·E·C
73	BAS70	VISH	shd	V _R <70B; I _E <200 mA; V _E (I _E =15 mA)<1.0B; I _R <0.1 mkA; C _D <2.0 nΦ; t _{RR} <5 hc	SOT23,SOD23	
73	BAS70	GS	shd	$V_R \le 70B$; $I_E \le 200 \text{ mA}$; $V_E (I_E = 15 \text{ mA}) \le 1.0B$; $I_R \le 0.1 \text{ mKA}$; $C_D \le 2.0 \text{ n}\Phi$; $t_{BR} \le 5 \text{ HC}$	SOT23,SOD23	
73	BAS70	DIOT	shd	$V_R < 70B$; $I_e < 200 \text{ mA}$; $V_E (I_e = 15 \text{ mA}) < 1.0B$; $I_R < 0.1 \text{ mkA}$; $C_D < 2.0 \text{ n}\Phi$; $t_{BR} < 5 \text{ Hz}$		7
73	BAS70	MCS	shd	V _R <70B; I _E <70 mA; V _E (I _E =15 mA)<1.0 B; I _R <0.1 mκA; C _D <2.0 nΦ; t _{DR} <5 hc	SOT23,SOD23	A·n.c.·K
73-	BAS70W	PHIL	shd	V _B <70B; I _E <70 MA; V _E (I _E =1 MA)<410 MB; C _B <2 nΦ	SOT323.SC70	122200000000000000000000000000000000000
730	BAS70	PHIL	shd	V _B <70B; I _E <70 MA; V _E (I _E =1 MA)<410 MB; C _D <2 nΦ	SOT23.SOD23	101111111111111111111111111111111111111
73p	BAS70W	PHIL	shd	V _B <70B; I _E <70 mA; V _E (I _E =1 mA)<410 mB; C _D <2 mΦ	SOT323.SC70	
73s	BAS70	INF	shd	V _B <70B; I _E <70 мA; V _E (I _E =15 мA)<1.0 B; I _B <0.1 мкA; C _D <2.0 пФ	SOT23.SOD23	
73t	BAS70W	PHIL	shd	V _B <70B; I _E <70 mA; V _E (I _E =1 mA)<410 mB; C _D <2 πΦ	SOT323.SC70	
74	BAS7004	VISH	shd×2	$V_R \le 70B$; $I_E \le 200 \text{ mA}$; $V_E (I_E = 15 \text{ mA}) \le 1.0B$; $I_R \le 0.1 \text{ mKA}$; $C_D \le 2.0 \text{ n}\Phi$; $t_{BR} \le 5 \text{ Hz}$		12/2/2010/19/20/2
74	BAS70-04	GS	shd×2	V _R <70 B; I _F <200 mA; V _E (I _E =15 mA)<1.0 B; I _B <0.1 mkA; C _D <2.0 nΦ; t _{BR} <5 hc	SOT23,SOD23	
74	BAS70-04	DIOT	shd×2	V _B <70 B; I _F <200 mA; V _E (I _F =15 mA)<1.0 B; I _B <0.1 mkA; C _D <2.0 nΦ; t _{BB} <5 hc	SOT23,SOD23	1112
74	BAS70-04	MCS	shd×2	V _B <70B; I _e <70 mA; V _e (I _e : 15 mA)<1.0 B; I _B <0.1 mxA; C _D <2.0 nΦ; I _{BB} <5 hc	SOT23,SOD23	
74	DTA114WE	ROHM	Dpnp	V _{C80} °50 B; I _C °100 MA; P _D °150 MBτ; h ₂₁ > 24; f _T >250 MΓμ; R ₁ /R ₂ °10/4.7 κOM	SOT416,SC75A	
74	DTA114WKA	ROHM	Dpnp	N ₂₈₀ +50 B; I _C =100 MA; P _D =200 MBT; h ₂₁ >24; f _T >250 MFu; R ₂ /R ₂ -10/4 7 KOM	SOT346,SC59	B-E-C
74	DTA114WUA	ROHM	Dpnp	V _{CB0} +550 B; I _C +100 xA; P _D +200 xBt; h ₂₁ >24; f _T >250 MFu; IR ₁ /R ₀ +10/4.7 kOM	SOT323,SC70	B·E·C
74-	BAS70-04W	PHIL	shd×2	$V_B < 70 B$; $I_E < 70 MA$; $V_E (I_E = 1 MA) < 410 MB$; $C_D < 2 n\Phi$	SOT323,SC70	A1-K2-K1,A2
74p	BAS7004	PHIL	shd×2	V _R <70B; I _E <70 mA; V _E (I _E =1 mA)<410 mB; C _D <2 mΦ	SOT23,SOD23	A1-K2-K1,A2
740	BAS7004W	PHIL	shd×2	V _B <70B; I _E <70 mA; V _E (I _E =1 mA)<410 mB; C _D <2 nΦ	SOT323.SC70	
74s	BAS7004	SIEM	shd×2	V _B <70B; I _E <70 мA; V _E (I _E =15 мA)<0.1 B; I _B <2.0 мкA; C _D <2.0 пФ	SOT23,SOD23	100000000000000000000000000000000000000
74s	BAS70-04	INF	shd×2	V _R <70B; I _E <70 mA; V _E (I _E =15 mA)<1.0 B; I _R <0.1 mxA; C _D <2.0 nΦ	SOT23,SOD23	
74s	BAS70-04T	INF		V _R <70B; I _E <70 mA; V _E (I _E =15 mA)<1.0 B; I _R <0.1 mxA; C _D <2.0 nΦ	SOT416,SC75A	-
74s	BAS7004W	SIEM	shd×2	V _R <70B; I _E <70 mA; V _E (I _E =15 mA)<1.0 B; I _R <0.1 mxA; C _R <2.0 nΦ	SOT323.SC70	-
74s	BAS70-04W	INF	shd×2	V _R <70B; I _e <70 MA; V _e (I _e : 15 MA)<1.0 B; I _e <0.1 MxA; C _n <2.0 πΦ	SOT323,SC70	
74t	BAS70-04W	PHIL	shd×2	V _R <70B; I _F <70 MA; V _F (I _F =1 MA)<410 MB; C _D <2 mΦ	SOT323.SC70	
75	BAS7005	VISH	shd×2	V_B <70 B; I_E <200 MA; V_B (I_E =15 MA)<1.0 B; I_B <0.1 MKA; C_D <2.0 n Φ ; t_{PB} <5 HC		
75	BAS70-05	GS	shd×2	$V_R < 70B$; $I_R < 200 \text{ MA}$; $V_R (I_R = 15 \text{ MA}) < 1.0B$; $I_R < 0.1 \text{ MKA}$; $C_D < 2.0 \text{ TW}$; $I_{RR} < 5 \text{ HC}$		
	DUDI UTUU	LAU.	JULIONE.	[48 - 10 D, 4 - 200 km, 4ptr- 10 km/s 1.0 D, ig - 0. 1 km/s, cg - 2.0 km/s, tpg - 0 mc	00160,00020	LILL WE WI'VE





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
75	BAS70-05	MCS	shd×2	$V_R < 70B$; $I_F < 70$ mA; $V_F (I_F = 15$ mA) < 1.0 B; $I_R < 0.1$ mrA; $C_D < 2.0$ n Φ ; $t_{RR} < 5$ H C	SOT23,SOD23	A1-A2-K1,K2
75-	BAS70-05W	PHIL	shd×2	$V_R < 70B$; $I_F < 70 \text{ mA}$; $V_F (I_F = 1 \text{ mA}) < 410 \text{ mB}$; $C_D < 2 \text{ m}$	SOT323,SC70	A1+A2+K1,K2
75p	BAS70-05	PHIL	shd×2	V _B <70B; I _E <70 мА; V _E (I _E =1 мА)<410 мВ; С _D <2 пФ	SOT23,SOD23	A1+A2+K1,K2
75p	BAS7005W	PHIL	shd×2	$V_B < 70B$; $I_E < 70 \text{ mA}$; $V_E (I_E = 1 \text{ mA}) < 410 \text{ mB}$; $C_D < 2 \text{ n}\Phi$; $t_{BB} < 0.1 \text{ Hz}$	SOT323,SC70	A1 • A2 • K1, K2
75s	BAS7005	SIEM	shd×2	V _B <70B; I _E <70 MA; V _E (I _E =15 MA)<1.0B; I _B <0.1 MKA; C _D <2.0 πΦ	SOT23,SOD23	A1-A2-K1,K2
75s	BAS70-05	INF	shd×2	V _B <70B; I _E <70 MA; V _E (I _E =15 MA)<1.0B; I _B <0.1 MKA; C _D <2.0 nΦ	SOT23,SOD23	A1-A2-K1,K2
75s	BAS7005W	SIEM	shd×2	V _B <70B; I _E <70 MA; V _E (I _E =15 MA)<1.0B; I _B <0.1 MKA; C _D <2.0 nΦ	SOT323,SC70	A1 · A2 · K1 K2
75s	BAS70-05W	INF	shd×2	V _B <70B; I _E <70 MA; V _E (I _E =15 MA)<1.0B; I _B <0.1 MKA; C _D <2.0 nΦ	SOT323.SC70	A1-A2-K1.K2
75t	BAS70-05	PHIL	shd×2	V _B <70B; I _E <70 mA; V _E (I _E =1 mA)<410 mB; C _D <2 πΦ	SOT23 SOD23	A1-A2-K1.K2
75t	BAS70-05W	PHIL	shd×2	V _R <70B; I _E <70 mA; V _E (I _E =1 mA)<410 mB; C _D <2 nΦ	S0T323,SC70	
75V	PZM75NB	PHIL	dz	V ₂ (I ₂₇ =2 MA)=70.079.0 B; Z ₂₇ (I ₂₇ =2 MA) < 175 Om	SOT346.SC59	
76	BAS7006	VISH	shd-2	V _R <70B; I _E <200 mA; V _E (I _E =15 mA)<1.0B; I _R <0.1 mkA; C _D <2.0 nΦ; t _{BR} <5 HC		17 71101 11
76	BAS70-06	GS	shd×2	V _R <70B; I _F <200 mA; V _F (I _F :15 mA)<1.0B; I _R <0.1 mxA; C _D <2.0 πΦ; t _{FR} <5 HC	SOT23.SOD23	
76	BAS70-06	DIOT	shd×2	V_R <70B; I_R <200 mA; V_E (I_R =15 mA)<1.0B; I_R <0.1 mrA; C_D <2.0 n Φ ; t_R <5 Hc	SOT23,SOD23	
76	BAS70-06	MCS	shd×2	V _R <70B; I _F <70 M3; V _F (I _F =15 M3)<1.0B; I _R <0.1 MKA; C _Ω <2.0 nΦ; I _{RR} <5 Hc	SOT23,SOD23	
76	DTA144WE	ROHM	Dono	V _{CR0} =50 B; I _{Crimon} =100 mA; P _D =200 mBτ; h ₂₁ >56; f _T >250 MΓц;	SOT416.SC75A	
10	DIATAWE	KUHM	Dhulo	V _{CB0} =50B, I _{G(max)} =100 MA; P _D =200 MBT; H ₂₁ 250; I _T 2250 MI II; R ₁ /R ₂ =47/22 kOM	501410,5C/5A	B.E.C
76	DTA144WKA	ROHM	Dpnp	V_{CB0} =50 B; I_C =30 mA; P_D =200 mBT; h_{21} >56; f_T >250 MFu; R_1/R_2 =47/22 kOm	SOT346,SC59	B·E·C
76	DTA144WUA	ROHM	Dpnp	V_{CB0} =50 B, $I_{C(max)}$ =100 MA; P_{D} =200 MB+; h_{21} >56; f_{7} >250 MFu; P_{1}/P_{2} =47/22 KOM	S0T323,SC70	B-E-C
76-	BAS70-06W	PHIL	shd×2	$V_R < 70B$; $I_F < 70 \text{ MA}$; $V_F (I_F = 1 \text{ MA}) < 410 \text{ MB}$; $C_D < 2 \text{ n}\Phi$	SOT323,SC70	K1 · K2 · A1,A2
76p	BAS70-06	PHIL	shd×2	$V_R < 70B$; $I_F < 70 \text{ mA}$; $V_F (I_F = 1 \text{ mA}) < 410 \text{ mB}$; $C_D < 2 \text{ m}$	SOT23,SOD23	K1 · K2 · A1, A2
76p	BAS7006W	PHIL	shd×2	$V_B < 70B$; $I_E < 70$ mA; $V_E (I_E = 1$ mA) < 410 mB; $C_D < 2$ m Φ ; $t_{BB} < 0.1$ mc	SOT323,SC70	K1 · K2 · A2,A1
76s	BAS7006	SIEM	shd×2	V _B <70B; I _E <70 MA; V _E (I _E =15 MA)<1.0B; I _B <0.1 MKA; C _D <2.0 nΦ	SOT23,SOD23	K1-K2-A1,A2
76s	BAS70-06	INF	shd×2	$V_B < 70B$; $I_E < 70 \text{ mA}$; $V_C (I_E = 15 \text{ mA}) < 1.0B$; $I_B < 0.1 \text{ mkA}$; $C_D < 2.0 \text{ m}$	SOT23,SOD23	K1-K2-A1,A2
76s	BAS7006W	SIEM	shd×2	$V_B < 70B$; $I_E < 70 \text{ mA}$; $V_C (I_E = 15 \text{ mA}) < 1.0B$; $I_B < 0.1 \text{ mkA}$; $C_D < 2.0 \text{ m}$	SOT323.SC70	K1-K2-A1.A2
76s	BAS70-06W	INF	shd×2	V _B <70B; I _E <70 MA; V _E (I _E =15 MA)<1.0B; I _B <0.1 MKA; C _D <2.0 nΦ	SOT323.SC70	K1-K2-A1.A2
76t	BAS70-06	PHIL	shd×2	V _B <70B; I _E <70 MA; V _E (I _E =1 MA)<410 MB; C _B <2 nΦ	SOT23.SOD23	
76t	BAS70-06W	PHIL	shd×2	V _B <70B; I _E <70 mA; V _E (I _E =1 mA)<410 mB; C _D <2 nΦ	SOT323.SC70	
7A	MMBR901LT1	MOT	non	V _{CB0} =25B, I _C =30 MA; P _D =300 MBT; h ₂₁ =30200	SOT23.SOD23	
7A	MMBR901LT3	MOT	non	V _{CPO} =25B; I _C =30 mA; P _D =300 mBT; h ₂₁ =30200	SOT23,SOD23	
7A5	PZM7.5NB2A	PHIL	dz×2	V ₂ (I ₂₁ =5 MA)=7.287.60 B; Z ₂₁ (I ₂₁ =5 MA) < 10 Om	SOT346.SC59	
7B	MMBR920LT2	MOT	non	V _{CB0} =20B; I _C =35 MA; P _D =268 MBT; I ₂₁ =25250; f _T =4500 MFu	SOT23.SOD23	
7D	HD4A	ZETEX	fid×2	V_B <35B; I_E <100 mA; V_E (I_E =10 mA)<1.0B; I_B <1.0 mKA; C_D <4.0 n Φ ; t_{BB} <6 HC		100000000000000000000000000000000000000
7D	MMBR931LT1	MOT	non	V _{CR0} =10B; I _C =5mA; P _C =150mBT; h ₂₁ =50150	SOT23,SOD23	The second secon
7E	FMMTA42R	ZETEX	non	V _{CBD} =300 B; I _C =200 MA; P _D =330 MBT; h _{P1} >40; f _T >50 MF _U	SOT23,SOD23	
7E	MMBR2060	MOT	non	V _{CF} =30B; I _C =200 MR; F _D =350 MB1; F _D =1750 WILL	SOT23,SOD23	
7E		MOT	- op	1 0 1 1	-	
	MMBR4957LT1		pnp	V _{CE} *30B; I _C *30MA; P _D *278 MBT; f _T *1.2 IT II	SOT23,SOD23	
7G	MMBR5031LT1	MOT	npn	V _{CBO} =15B; I _C =20мA; P _D =300мBт; h ₂₁ =25300; f _T =1000 МГц	SOT23,SOD23	
7H	KST5179	SAMS	npn	V_{CB0} =20B; I_C =50mA; P_D =350mBT; h_{21} >25; f_T >900MFu	SOT23,SOD23	LOSING HONORS
7H	MMBR5179LT1	MOT	npn	V _{CB0} =20B; I _C =50мA; P _D =375мBт; h ₂₁ >25; f _T =1400МГц	SOT23,SOD23	
7J	FMMT38C	ZETEX	npn	V _{CB0} =80 B; I _C =300 мA; P _D =330 мBт; h ₂₁ >5000	SOT23,SOD23	
7K	MMBR2857LT1	MOT	npn	V _{CE} =15B; I _C =40MA; f _T =4ΓΓц	SOT23,SOD23	
7M	BCW66HR	ZETEX	npn	V _{CB0} =75B; I _C =800мA; P _D =330мBт; h ₂₁ =250630; f _T >100МГц	SOT23,SOD23	
7M	MMBR521LT1	MOT	pnip	V _{CB0} =20B; I _C =70мA; P _D =333мBт; h ₂₁ =25125; f _T =3400МГц	SOT23,SOD23	
7N	BCW68HR	ZETEX	pnp	V_{CB0} =60 B; I_C =800 mA; P_D =330 mBr; h_{21} =250630; f_T >100 M Γ_{IJ}	SOT23,SOD23	
7N	MMBR941BLT1	MOT	npn	V _{CB0} =20 B; I _C =50 мА; P _D =250 мВт; h ₂₁ =100200; f _T =8000 МГц	SOT23,SOD23	DESCRIPTION
7N	MMBR941BLT3	MOT	npn	V _{CB0} =20 B; I _C =50 мА; P _D =250 мВт; h ₂₁ =100200; f _T =8000 МГц	SOT23,SOD23	1572
7P	BCW66FR	ZETEX	npn	V _{CB0} =75B; I _C =800 мA; P _D =330 мВт; h ₂₁ =100250; f _T >100 МГц	SOT23,SOD23	B·E·C
7P	BCW66FR	SGS	npn	$V_{CB0}=75B$; $I_C=800$ mA; $P_0=350$ mBT; $h_{21}=100250$; $f_T>100$ M Γ_{II}	SOT23,SOD23	
7P	MMBR911LT1	MOT	npn	V_{CB0} =20 B; I_C =60 mA; P_D =300 mBT; h_{21} =30200; f_T =6000 MF $_{4}$	SOT23,SOD23	B·E·C
7R	MMBR536	MOT	pnp	V _{CB0} =10B; I _C =10mA	SOT23,SOD23	B·E·C

SOT490 TESM VMT3 1 3 SOT523 SOT323 SOT23-3 1 3 SOT523 SOT323 SOT3

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
7T	BCW68FR	ZETEX	pnp	V _{CB0} =60 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =100250; f _T >100 МГц	SOT23,SOD23	B·E·C
7V5	PZM7.5NB	PHIL	dz	V ₂ (I _{2T} =5 mA)=7.067.84 B; Z _{2T} (I _{2T} =5 mA) < 10 Om	SOT346,SC59	A·n.c.·K
7X	MMBR571LT1	MOT	npn	V _{CB0} =20 B; I _C =80 mA; P _D =330 mBT; h ₂₁ =50300; f _T =8000 MF _{LL}	SOT23,SOD23	B-E-C
7Y	MMBR941LT1	MOT	npn	V _{CR0} =20 B; I _C =50 mA; P _D =250 mBT; h ₂₁ =50200; f _T =8000 MFi ₄	SOT23,SOD23	B·E·C
7Y	MMBR941LT3	MOT	npn	V _{CR0} =20 B; I _C =50 mA; P _D =250 mBT; h ₂₁ =50250; f _T =8000 MF _I	SOT23,SOD23	B-E-C
-7Y	PDTB123YT	PHIL	Dpnp	V _{CB0} =50 B; I _C =500 MA; P _D =250 MBT; h ₂₁ >70; 2.2 KOM/10 KOM	SOT23,SOD23	B-E-C
7Z	MMBR951LT1	MOT	npn	V _{GR0} =20 B; I _G =100 MA; P _D =322 MBr; h ₂₁ =50200; f _T =8000 MFu	SOT23,SOD23	B·E·C
8.2	01BZA8.2	TOSH	pz×2	V ₂ (I ₂₇ =5 MÅ)=7.78.7 B; I _R (V _R =6.5 B)<0.5 MKÅ	SOT323,SC70	K1-K2-A1,A2
8.2X	02CZ8.2	TOSH	dz	V ₂ (I _{ZT} =5 mA)=7.708.70 B; I ₁ (V _B =6.5B)<0.5 mkA; Z _{ZT} (I _{ZT} =0.5 mA)<120 0m	SOT346.SC59	A·n.c.·K
81A	FMMZ5250	ZETEX	dz	V ₂ =20B; Z ₂₇ (I ₂ =6.2 mA)=250m	SOT23,SOD23	A·n.c.·K
81A	PMBZ5250B	PHIL	dz	$V_Z(I_{ZT}=6.2 \text{ mA})=20 \text{ B}; I_L(V_B=15 \text{ B})<0.1 \text{ m/sA}; Z_{ZT}(I_{ZT}=6.2 \text{ mA})<600 \text{ Om}; I_{ZM}=200 \text{ mA}$	SOT23,SOD23	A•n.c.•K
81A	TMPZ5250	ALLEG	dz	V _Z (I _{ZT} =6.2 mA) = 19.021.0B; I _L (V _R =15.0 B) < 0.1 mkA; Z _{ZT} (I _{ZT} =6.2 mA) < 250m	SOT23,SOD23	A·n.c.·K
81A	MMBZ5250B	VISH	dz	V ₂ (I _{ZT} =6.2 mA)=19.021.0B; I _B <01 mrA	SOT23,SOD23	A•n.c.•K
81A	MMBZ5250BLT1	ON	dz	V ₂ (I _{ZT} =6.2 mA)=19.021.0 B; I _R <01 mkA	SOT23,SOD23	A•n.c.•K
81B	FMMZ5251	ZETEX	dz	Vz=22B; Zzt(Iz=5.6 mA)=29 Om	SOT23,SOD23	A•n.c.•K
81B	PMBZ5251B	PHIL	dz	$V_Z(I_{ZT}$ =5.6 mA)=22 B; $I_L(V_B$ =17 B)<0.1 mrA; $Z_{ZT}(I_{ZT}$ =5.6 mA)<600 Om; I_{ZM} =200 mA	SOT23,SOD23	A•n.c.•K
81B	TMPZ5251	ALLEG	dz	$V_2(I_{ZT}=5.5 \text{ mA}) = 20.923.1 \text{ B; } I_L(V_B=17.0 \text{ B}) \le 0.1 \text{ m/sA;} $ $Z_{ZT}(I_{ZT}=5.5 \text{ mA}) \le 29 \text{ Om}$	SOT23,SOD23	
81B	MMBZ5251B	VISH	dz	V ₂ (I _{ZT} =5.6 mA)=20.923.1 B; I _R <0.1 mкA	SOT23,SOD23	
81B	MMBZ5251BLT1	ON	dz	V ₂ (I _{ZT} =5.6 mA)=20.923.1 B; I _R <0.1 mkA	SOT23,SOD23	A·n.c.·K
81C	FMMZ5252	ZETEX	dz	Vz=24B; Zz1(Iz=5.2 mA)=33 Om	SOT23,SOD23	A·n.c.·K
81C	PMBZ5252B	PHIL	dz	$V_Z(I_{ZT}$ =5.2 mA)=24 B; $I_L(V_R$ =18 B)<0.1 mKA; $Z_{ZT}(I_{ZT}$ =5.2 mA)<600 OM; I_{ZM} =200 mA	SOT23,SOD23	A•n.c.•K
81C	TMPZ5252	ALLEG	dz	V _Z (I _{ZT} =5.2 mA) = 22.825.2B; I _L (V _R =18.0 B) ≤ 0.1 m/sA; Z _{ZT} (I _{ZT} =5.2 mA) ≤ 33 Om	SOT23,SOD23	A+n.c.+K
81C	MMBZ5252B	VISH	dz	V _Z (I _{ZT} =5.2 mA)=22.825.2 B; I _R <0.1 mkA	SOT23,SOD23	A·n.c.·K
81C	MMBZ5252BLT1	ON	dz	V ₂ (I _{ZT} =5.2 mA)=22.825.2 B; I _R <0.1 mкA	SOT23,SOD23	A·n.c.·K
81D	FMMZ5253	ZETEX	dz	Vz=25B; Zzt(Jz=5mA)=35 Om	SOT23,SOD23	A•n.c.•K
81D	PMBZ5253B	PHIL	dz	$V_Z I_{ZT}$ = 5.0 mA) = 25 B; $I_L V_B$ = 19 B) < 0.1 m/kA; $Z_{ZT} I_{ZT}$ = 5.0 mA) < 600 OM; I_{ZM} = 200 mA	SOT23,SOD23	
81D	TMPZ5253	ALLEG	dz	V _Z (I _{ZT} =5.0 mA) = 23.826.3 B; I _L (V _B =19.0 B) < 0.1 m/A; Z _{Z1} (I _{ZT} =5.0 mA) < 35 Om	SOT23,SOD23	A·n.c.·K
81D	MMBZ5253B	VISH	dz	V ₂ (I _{ZT} =5.0 mA)=23.7526.25B; I _R <0.1 mkA	SOT23,SOD23	1900 100 100 100
81D	MMBZ5253BLT1	ON	dz	V ₂ (I _{ZT} =5.0 mA)=23.7526.25B; I _R <0.1 mkA	SOT23,SOD23	A•n.c.•K
81E	FMMZ5254	ZETEX	dz	Vz=27 B; Zz1(Iz=4.6 mA)=41 Om	SOT23,SOD23	
81E	PMBZ5254B	PHIL	dz	$\frac{V_Z(I_{ZT}\!=\!4.6\text{mA})\!=\!27\text{B;}\ I_{\xi}(V_{R}\!=\!21\text{B})\!<\!0.1\text{m/KA;}\ Z_{ZT}(I_{ZT}\!=\!4.6\text{mA})\!<\!600\text{OM;}}{I_{ZM}\!=\!200\text{mA}}$	SOT23,SOD23	
81E	TMPZ5254	ALLEG	dz	$ \begin{array}{l} V_2(I_{ZT}\!\!=\!\!4.6\text{mA})\!\!=\!\!25.7284B;I_L\!\{V_B\!\!=\!\!21.0B\}\!\!<\!\!0.1\text{mkA};\\ Z_{ZT}\{I_{ZT}\!\!=\!\!4.6\text{mA}\}\!\!<\!\!41.0\text{m} \end{array} $	SOT23,SOD23	0
81E	MMBZ5254B	VISH	dz	V ₂ (I _{ZT} =5.0 mA)=25.6528.35B; I _R <0.1 mkA	SOT23,SOD23	A·n.c.·K
81E	MMBZ5254BLT1	ON	dz	V ₂ (I _{ZT} =5.0 mA)=25.6528.35B; I _R <0.1 mkA	SOT23,SOD23	A·n.c.·K
81F	FMMZ5255	ZETEX	dz	Vz=28B; Zz1(Iz=4.5 mA)=44Om	SOT23,SOD23	A·n.c.·K
81F	PMBZ5255B	PHIL	dz	$\frac{V_Z(I_{ZT}\!\!=\!4.5\text{mA})\!\!=\!28B;I_L\!(V_B\!\!=\!21B)\!<\!0.1\text{m/KA};Z_{ZT}\!(I_{ZT}\!\!=\!4.5\text{mA})\!<\!600\text{OM};}{I_{ZM}\!\!=\!200\text{mA}}$	SOT23,SOD23	A·n.c.·K
81F	TMPZ5255	ALLEG	dz	$V_2(I_{ZT}^{-4.5 \text{ mA}}) = 26.629.4 \text{ B; } I_L(V_R^{-2.1.0 \text{ B}}) \le 0.1 \text{ m/sA;} $ $Z_{ZT}(I_{ZT}^{-4.5 \text{ mA}}) \le 44.0 \text{m}$	SOT23,SOD23	A•n.c.•K
81F	MMBZ5255B	VISH	dz	V ₂ (I _{ZT} =4.5 mA)=26.629.4B; I _R <0.1 mkA	SOT23,SOD23	A·n.c.·K
81F	MMBZ5255BLT1	ON	dz	V ₂ (I _{ZT} =4.5 mA)=26.629.4 B; I _R <0.1 mrA	SOT23,SOD23	A·n.c.·K
81G	FMMZ5256	ZETEX	dz	Vz=30B; Zzt(Iz=4.2 mA)=49 Om	SOT23,SOD23	A•n.c.•K
81G	PMBZ5256B	PHIL	dz	$V_2(I_{ZT}=4.2 \text{ mA})=30 \text{ B}; I_2(V_{R}=23 \text{ B})<0.1 \text{ m/sA}; Z_{ZT}(I_{ZT}=4.2 \text{ mA})<600 \text{ Om}; I_{ZM}=200 \text{ mA}$	SOT23,SOD23	A·n.c.·K





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
31G	TMPZ5256	ALLEG	dz	V ₂ (I _{ZT} =4.2 mA)=28.531.5 B; I ₂ (V _B =23.0 B)<0.1 mkA; Z _{ZT} (I _{ZT} =4.2 mA)<49.0 m	SOT23,SOD23	A•n.c.•K
31G	MMBZ5256B	VISH	dz	V _Z (I _{ZT} =4.2 mA)=28.531.5 B; I _B <0.1 msA	SOT23,SOD23	A·n.c.·K
31G	MMBZ5256BLT1	ON	dz	V _Z (I _{ZT} =4.2 mA)=28.531.5 B; I _B <0.1 mkA	SOT23,SOD23	A+n.c.+K
31H	FMMZ5257	ZETEX	dz	Vz=33 B; Zz(Iz=3.8 mA)=58 Om	SOT23,SOD23	A+n.c.+K
81H	PMBZ5257B	PHIL	dz	$V_{Z}(I_{ZT}^{-3}.8 \text{ mA})^{-3}.3B$; $I_{L}(V_{P}^{-2}.5B) < 0.1 \text{ mKA}$; $Z_{ZT}(I_{ZT}^{-3}.8 \text{ mA}) < 600 \text{ Om}$; $I_{ZM}^{-2}.200 \text{ mA}$	SOT23,SOD23	A•n.c.•K
81H	TMPZ5257	ALLEG	dz	V _X (I _{ZT} =3.8 mA)=31.434.7 B, I _L (V _R =25.0 B)<0.1 mxA; Z _{ZT} (I _{ZT} =3.8 mA)<58 Om	SOT23,SOD23	A•n.c.•K
31H	MMBZ5257B	VISH	dz	V _Z (I _{ZT} =3.8 mA)=31.3534.65 B; I _R <0.1 mкA	SOT23,SOD23	A+n.c.+K
81H	MMBZ5257BLT1	ON	dz	V _Z (I _{ZT} =3.8 mA)=31.3534.65B; I _R <0.1 mkA	SOT23,SOD23	A+n.c.+K
31J	MMBZ5258B	VISH	dz	V _Z (I _{ZT} =3.4 mA)=34.237.8 B; I _R <0.1 msA	SOT23,SOD23	A·n.c.·K
81J	MMBZ5258BLT1	ON	dz	V _Z (I _{ZT} =3.4 mA)=34.237.8 B; I _R <0.1 msA	SOT23,SOD23	A·n.c.·K
81K	MMBZ5259B	VISH	dz	V ₂ (I ₂₇ =3.2 mA)=37.0541.0 B; I _B <0.1 mcA	SOT23,SOD23	A+n.c.+K
81K	MMBZ5259BLT1	ON	dz	V ₂ (I ₂₇ =3.2 mA)=37.0541.0 B; I _B <0.1 mKA	SOT23,SOD23	A+n.c.+K
81L	MMBZ5260BLT1	ON	dz	V ₂ (I ₂₁ =3 mA)=40.8545.15 B; I ₈ <0.1 mkA	SOT23,SOD23	A·n.c.·K
81M	MMBZ5261B	VISH	dz	V _Z (I _{ZT} =2.7 mA)=44.6549.35 B; I _B <0.1 mrA	SOT23,SOD23	A+n.c.+K
81M	MMBZ5261BLT1	ON	dz	V _Z (I _{ZT} =2.7 mA)=44.6549.35B; I _R <0.1 mkA	SOT23,SOD23	A·n.c.·K
81N	MMBZ5262B	VISH	dz	V ₂ (I ₂₇ =2.5 mA)=48.4553.55 B; I _B <0.1 mKA	SOT23,SOD23	A·n.c.·K
81N	MMBZ5262BLT1	ON	dz	V ₂ (I ₂₇ =2.5 mA)=48.4553.55 B; I _B <0.1 mKA	SOT23.SOD23	A·n.c.·K
81P	MMBZ5263B	VISH	dz	V ₂ (I ₇₇ =2.2 mA)=53.2058.80 B; I _R <0.1 mKA	SOT23.SOD23	A+n.c.+K
81P	MMBZ5263BLT1	ON	dz	V-(I ₂₇ =2.2 mA)=53.2058.80 B; I _B <0.1 mKA	SOT23,SOD23	A·n.c.·K
81Q	MMBZ5264B	VISH	dz	V _A (I ₂₇ =2.1 mA)=57.0063.00 B; I _B <0.1 mKA	SOT23.SOD23	
310	MMBZ5264BLT1	ON	dz	V _Z (I _{ZT} =2.1 mA)=57.0063.00B; I _B <0.1 mkA	SOT23.SOD23	A·nc·K
BIR	MMBZ5265B	VISH	dz	V _X (I _{ZT} =2 MA)=58.9065.10 B; I _B <0.1 MKA	SOT23.SOD23	
BIR	MMBZ5265BLT1	ON	dz	V _Z (I _{ZT} =2 mA)=58.9065.10 B; I _B <0.1 mkA	SOT23.SOD23	
81S	MMBZ5266B	VISH	dz	V ₂ (I _{2T} =1.8 mA)=64.6071.40 B; I _R <0.1 mкA	SOT23, SOD23	
81S	MMBZ5266BLT1	ON	dz	V _X (I _{ZZ} =1.8 mA)=64.6071.40 B; I _B <0.1 mKA	SOT23.SOD23	
81T	MMBZ5267B	VISH	dz	V _X (I _{ZI} =1.7 mA)=71.2578.75B; I _R <0.1 mkA	SOT23,SOD23	Committee of the Commit
81T	MMBZ5267BLT1	ON	dz	V _x (I _{zz} =1.7 mA)=71.2578.75B; I _R <0.1 mkA	SOT23 SOD23	
81U	MMBZ5268BLT1	ON	dz	V _X (I ₂₇ =1.5 inA)=77.9086.10B; I ₀ <0.1 inKA	SOT23.SOD23	
81V	MMBZ5269BLT1	ON	dz	V _X (I _{ZI} =1.4 mA)=82.6591.35B; I _R <0.1 mkA	SOT23.SOD23	***************************************
81W	MMBZ5270BLT1	ON	dz	V _x (I _{zz} =1.4 mA)=86.4595.55B; I _R <0.1 mkA	SOT23,SOD23	
83	BAT68	SIEM	shd	V _B <8B; I _E <130 мА; V _E (I _E =10 мА)<0.5B; I _B <0.1 мкА; C _D <1.0 пФ	SOT23.SOD23	
83s	BAT68	INF	shd	V _P <8B; I _E <130 κA; V _E (I _E =10 κA)<0.5B; I _P <0.1 κκA; C _D <1.0 πΦ	SOT23.SOD23	
83s	BAT68W	INF	shd×2	V _B <8B; I _E <130 κA; V _E (I _E =10 κA)<0.5B; I _B <0.1 κκA; C _D <1.0 πΦ	SOT323.SC70	Personal Property and Property
84	BAT6804	SIEM	shd×2	$V_R \le BB$; $I_F \le 130 \text{ MA}$; $V_F (I_F = 10 \text{ MA}) \le 0.5 \text{ B}$; $I_R \le 0.1 \text{ MKA}$; $C_D \le 1.0 \text{ n} \Phi$	SOT23,SOD23	
84	DTC114WE	ROHM	Dnpn	V_{CB0}^{-} 50B, I_C^{+} 100mA; P_D^{-} 150mB τ ; h_{21}^{+} 24; f_T^{+} 250 MF u ; $P_{11}P_{0}$ =10/4.7 kOm	SOT416,SC75A	
84	DTC114WKA	ROHM	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _D =200 mBr; h ₂₁ > 24; f _T >250 MFu; R ₁ /R ₂ =10/4.7 kOm	SOT346,SC59	B·E·C
84	DTC114WUA	ROHM	Dnpn	V_{CB0} =50B; I_C =100 MA; P_D =200 MBT; h_{21} >24; f_T >250 MFu; R_1/R_2 =10/4.7 KOM	S0T323,SC70	B·E·C
34s	BAT68-04	INF	shd×2	$V_R \le 8B$; $I_E \le 130$ mA; $V_E (I_E = 10$ mA) ≤ 0.5 B; $I_R \le 0.1$ mrA; $C_D \le 1.0$ n Φ	SOT23,SOD23	A1-K2-K1,A
34s	BAT68-04W	INF	shd×2	V _B <8B; I _E <130 мA; V _E (I _E =10 мA)<0.5B; I _B <0.1 мкA; C _D <1.0 пФ	SOT323,SC70	A1-K2-K1.A
35	BAT6805	SIEM	shd×2	V _B <8B; I _E <130 мA; V _E (I _E =10 мA)<0.5B; I _B <0.1 мкА; C _D <1.0 пФ	SOT23,SOD23	
85A	MMBD1701A	FAIR	dl	V _B <30B; I _E =50 мA; V _E (I _E =50 мA)<1.1B; C _D <1 пФ; t _{BB} <1 нс	SOT23,SOD23	to the top
35s	BAT68-05	INF	shd×2	V _B <8B; I _E <130 мA; V _E (I _E =10 мA)<0.5B; I _B <0.1 мкA; C _D <1.0 пФ	SOT23.SOD23	SECTION SAME
35s	BAT68-05W	INF	shd×2	V _B <8B; I _E <130 мА; V _E (I _E =10 мА)<0.5B; I _B <0.1 мкА; C _D <1.0 пФ	SOT323.SC70	
36	BAT6806	SIEM	shd×2	V _B <8B; I _F <130 мA; V _F (I _F =10 мA)<0.5B; I _B <0.1 мкA; C _D <1.0 пФ	SOT23,SOD23	
36	DTC144WE	ROHM	Dnpn	V _{CB0} =50B; I _{C(msx)} =100 mA; P ₀ =150 mBτ; h ₂₁ >56; f ₁ >250 MΓu; R ₁ /R ₂ =47/22 κOm	SOT416,SC75A	

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
B6	DTC144WUA	ROHM	Dnpn	$\begin{array}{l} V_{\rm CB0} = \! 50 B_{\rm i} I_{\rm C(max)} = \! 100 \rm mA; P_D = \! 200 mBT; h_{21} \! > \! 56; f_T \! > \! 250 M\Gamma u; \\ R_1/R_2 = \! 47/22 \kappa O_{\rm M} \end{array}$	SOT323,SC70	B-E-C
B6s	BAT68-06	INF	shd×2	V _R <8B; I _F <130 мА; V _F (I _F =10 мА)<0.5 B; I _R <0.1 мкА; С _D <1.0 пФ	SOT23,SOD23	K1·K2·A1,A2
B6s	BAT68-06W	INF	shd×2	V _R <8B; I _E <130 mA; V _E (I _E =10 mA)<0.5 B; I _R <0.1 mxA; C _D <1.0 nΦ	SOT323,SC70	K1-K2-A1,A2
B7A	MMBD1703A	FAIR	dl×2	$V_B < 30B$; $I_E = 50 \text{ mA}$; $V_E (I_E = 50 \text{ mA}) < 1.1B$; $C_D < 1 \text{ n}\Phi$; $t_{BB} < 1 \text{ Hz}$	SOT23,SOD23	A1-K2-K1,A2
88A	MMBD1704A	FAIR	dk2	V _B <30B; I _F =50мA; V _E (I _F =50мA)<1.1B; C _D <1пФ; t _{BB} <1нс	SOT23,SOD23	A1-A2-K1,K2
89A	MMBD1705A	FAIR	dl×2	V _B < 30 B; I _E =50 mA; V _E (I _E =50 mA) < 1.1 B; C _D < 1 nΦ; t _{BB} < 1 HC	SOT23,SOD23	K1-K2-A1,A2
8A	2DA1774Q	DIODS	ono	V _{CE0} =50B; I _C =150 мA; P ₀ =150 мВт; h ₂₁ =120270; f _T =140 МГц	SOT523	B-E-C
A8	DTC114EET1	MOT	Dopon	V _{CR0} =50B; I _C =100 MA; P _D =150 MBT; h ₂₁ >30; f _T >250 MFu; R ₁ /R ₂ =10/10 kOM	SOT416.SC75A	B·E·C
8A	MUN2211T1	ON	Dnpn	V _{CBO} =50B; I _S =100 mA; P _D =230 mBr; h ₂₁ > 35; 10 kOm/10 kOm	SOT346.SC59	
8A	MUN5211T1	ON	Dnon	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBr; h ₂₁ >35; 10 kOm/10 kOm	SOT323.SC70	
8A	MMBZ5226B	VISH	dz	V ₂ (I _{2T} =20 mA)=3.133.47 B; I _B <25 mrA	SOT23,SOD23	
8A	MMBZ5226BLT1	ON	dz	V ₂ (I _{2T} =20 mA)=3.133.47 B; I _R <25 m;A	SOT23,SOD23	The same of the sa
8A2	PZM8.2NB2A	PHIL	dz×2	V ₂ (I ₇₁ =5 mA)=8.028.36 B; Z ₇₁ (I ₇₁ =5 mA)<10 Om	SOT346,SC59	100000000000000000000000000000000000000
8AA	BC846A	SAMS	non	V _{D80} =80 B; I _C =100 mA; P _D =310 mBr; h ₂₁ =110220; f _T >300 MFu	SOT23.SOD23	
BA8	BC846A	FAIR	ngn	V _{CB0} =80 B; I _C =100 MA; P _D =150 MBr; h ₂₁ =110220; f _T =300 MFц	SOT23,SOD23	
8AAx	STM809L	STM	mrc	V _{тв} -4.63B; V _{пп} -1.25.5B; I _{пс} <15мкА	SOT23,SOD23	
SAB	BC846B	SAMS		111 00	SOT23,SOD23	
SAB	D.C. C. C. C.	FAIR	npn	V _{C80} =80 B; I _C =100 mA; P _D =310 mBr; h ₂₁ =200450; f _T >300 MFu		
8ABx	BC846B		npn	V _{C80} =80 B; I _C =100 мА; P _D =150 мВт; h ₂₁ =200450; f _T =300 МГц	SOT23,SOD23	
	STM809M	STM	mrc	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <15 MKA	SOT23,SOD23	
8AC	BC846C	SAMS	npn	V_{C80} =80 B; I_C =100 mA; P_D =310 mBt; h_{21} =420800; f_T >300 M Γ_{LL}	SOT23,SOD23	10000 00
8AC	BC846C	FAIR	npn	V _{CB0} =80 B; I _C =100 mA; P ₀ =310 mBr; h ₂₁ =420800; f _T >300 MF _{LI}	SOT23,SOD23	-
8ACx	STM809T	STM	mrc	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{CC} <15mKA	SOT23,SOD23	- 04
8ADx	STM809S	STM	mrc	V _{тR} =2.93B; V _{DD} =1.25.5B; I _{CC} <15мкА	SOT23,SOD23	
8AEx	STM809R	STM	mrc	V _{тR} =2.63B; V _{DD} =1.25.5B; I _{CC} <15мкА	SOT23,SOD23	
8AFx	STM810L	STM	mrc	V _{TR} =4.63B; V _{DD} =1.25.5B; I _{CC} <15mкA	SOT23,SOD23	
8AGx	STM810M	STM	mrc	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <15 мкA	SOT23,SOD23	VSS+RST+V _{CE}
xHA8	STM810T	STM	mrc	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{CC} <15mкA	SOT23,SOD23	VSS-RST-V _{CC}
8AJx	STM810S	STM	mrc	V _{TR} =2.93B; V _{DD} =1.25.5B; I _{CC} <15мкA	SOT23,SOD23	VSS+RST+V _{CX}
8AKx	STM810R	STM	mrc	V _{TR} =2.63B; V _{DD} =1.25.5B; I _{CC} <15мкA	SOT23,SOD23	VSS+RST+V _{OX}
8B	2DA1774R	DIODS	pnp	V _{CEO} =50B; I _C =150 мA; P _D =150 мВт; h ₂₁ =180390; f _T =140 МГц	SOT523	B·E·C
8B	DTC124EET1	MOT	Dnpn	V_{C80} =50B; $I_{C(res)}$ =100 mA; P_0 =150 mBT; h_{21} >56; f_T >250 MF $_{41}$; P_1/P_2 =22/22 kOm	SOT416,SC75A	B-E-C
8B	MUN2212T1	ON	Dnpn	V ₀₈₀ =50B; I ₀ =100 мA; P ₀ =230 мВг; h ₂₁ >60; 22 кОм/22 кОм	SOT346,SC59	B-E-C
8B	MUN5212T1	ON	Dnpn	V _{GB0} =50 B; I _G =100 MA; P _D =200 MBT; h ₂₁ >60; 22 KOM/22 KOM	SOT323,SC70	B·E·C
8B	MMBZ5227B	VISH	dz	V ₂ (I ₂₇ =20 mA)=3.423.78 B; I _R < 15 m kA	SOT23,SOD23	A·n.c.·K
8B	MMBZ5227BLT1	ON	dz	V ₂ (I _{2T} =20 mA)=3.423.78B; I _R <15 mkA	SOT23,SOD23	
8BA	BC847A	FAIR	ngn	V _{CR0} =50 B; I _C =100 mA; P _D =250 mBr; h _M =110220; f _T >100 MFu	SOT23,SOD23	
8BB	BC847B	SAMS	npn	V _{C80} =50 B; I _C =100 mA; P _D =310 mBr; h ₂₁ =200450; f _T >300 MFu	SOT23,SOD23	-
8BB	BC847B	FAIR	npn	V _{CBB} =50 B; I _C =100 mA; P _D =310 mB _T ; h ₂₁ =200450; f _T >300 MF _U	SOT23,SOD23	
8BC	BC847C	SAMS	non	V _{C80} =50 B; I _C = 100 mA; P _D = 310 mBr; h ₂₁ =420800; f ₁ > 300 MFu	SOT23,SOD23	
8BC	BC847C	FAIR	ngn	V _{CB0} =50 B; I _C =100 MA; P _D =310 MBT; h ₂₁ =420800; f _T >300 MF _U	SOT23,SOD23	
8C	2DA1774S	DIODS	pnp	V _{CE0} =50B; I _C =150 MA; P _D =150 MBT; h ₂₁ =270560; f _T =140 MFu	SOT523	B-E-C
8C	DTC144EET1	MOT	Dnpn	V_{C80} =50B; $I_{C(meq)}$ =100; P_{D} =150 MBT; I_{D1} >68; f_{T} >250 MFu; P_{T}/P_{T} =47/47 kOM	SOT416,SC75A	
8C	MUN2213T1	ON	Dnon	V _{CBO} =50B; I _C =100 mA; P _D =230 mBr; h ₂₁ >80; 47 kOm/47 kOm	SOT346.SC59	B-E-C
8C	MUN5213T1	ON	Dnpn	V _{G80} =50B; I _C =100 mA; P _D =200 mBr; h ₂₁ >80; 47 кОм/47 кОм	SOT323,SC70	
8C	MMBZ5228B	VISH	dz	V ₂ (I ₂₇ =20 mA}=3.704.10B; I _B <10 m/A	SOT23.SOD23	
8C	MMBZ5228BLT1	ON	dz	V ₂ (I _{2T} =20 MA)=3.704.10B; I _R <10 MrA	SOT23,SOD23	
8CA	BC848A	SAMS				200700000000000000000000000000000000000
	The Control of the Co		npn	V _{C80} =30 B; I _C =100 mA; P _D =310 mBr; h ₂₁ =110220; f _T >300 MFu	SOT23,SOD23	
8CA	BC848A	FAIR	npn	V _{G80} =30 B; I _C =100 MA; P ₀ =310 MBr; h ₂₁ =110220; f ₇ >300 MFц	SOT23,SOD23	
8CB	BC848B	SAMS	npn	V_{CB0} =30 B; I_C =100 mA; P_D =310 mBr; h_{21} =200450; f_T >300 M Γ_{LL}	SOT23,SOD23	R.E.C





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
8CB	BC848B	FAIR	npn	V _{CB0} =30 B; I _C =100 мA; P _D =310 мВт; h ₂₁ =200450; f _T >300 МГц	SOT23,SOD23	B·E·C
BCC	BC848C	SAMS	npn	V _{CBO} =30B; I _C =100мA; P _D =310мBт; h ₂₁ =420800; f _T >300МГц	SOT23,SOD23	B·E·C
BCC	BC848C	FAIR	npn	V _{CB0} =30 B; I _C =100 мA; P _D =310 мВт; h ₂₁ =420800; f _T >300 МГц	SOT23,SOD23	B·E·C
BD	2DC4617Q	DIODS	npn	V _{GB0} =60 B; I _G =150 мА; P _D =150 мВт; h ₂₁ =120270; f _T =180 МГц	SOT523	B·E·C
BD B	DTC114YET1	MOT	Dnpn	V _{CB0} =50 B; I _C =100 mA; P _D =150 mBT; h ₂₁ >68; f _T >250 MFu; R ₁ /R ₂ =10/47 kOm	SOT416,SC75A	B·E·C
8D	MMBZ5229B	VISH	dz	V _A (I ₇₇ =20 mA)=4.084.52 B; I _B <5 mkA	SOT23,SOD23	A·n.c.·K
8D	MMBZ5229BLT1	ON	dz	V ₂ (I ₂₇ =20 mA)=4.084.52 B; I _B <5 mkA	SOT23,SOD23	A+n.c.+K
8D	MUN2214T1	ON	Dnon	V _{CRO} =50 B; I _C =100 mA; P _D =230 mBT; h ₂₁ > 80; 10 kOm/47 kOm	SOT346,SC59	B·E·C
BD	MUN5214T1	ON	Dnon	V _{CR0} =50 B; I _C = 100 mA; P _D =200 mB _T ; h ₂₁ >80; 10 kOm/47 kOm	SOT323,SC70	B·E·C
BD	TMPZ5229	ALLEG	dz	V ₂ (I ₂₇ =20 mA)=4.084.52 B; I ₁ (V _B =1.0 B) < 5.0 mxA; Z ₂₇ (I ₂₇ =20 mA) < 22 0m	SOT23,SOD23	
BDA	BC849A	SAMS	non	V _{CB0} =30B; I _C =100mA; P _D =310mBr; h ₂₁ =110220; f _T >300MFц	SOT23,SOD23	
RDA	BC849A	FAIR	non	V _{CR0} =30B; I _C =100MA; P _D =310MBT; h ₂₁ =110220; f _T >300MFц	SOT23.SOD23	1001/25/1191
BDB	BC849B	FAIR	non	V _{CBO} -30B; I _C =100мA; P _D =150мBr; I ₂₁ =110220, тузоотипц V _{CBO} -30B; I _C =100мA; P _D =150мBr; I ₂₁ =200450; F _T =300МГц	SOT23,SOD23	0.0000000000000000000000000000000000000
BDC	BC849C	FAIR	non	Vcen=30B; Ic=100MA; Pn=150MBT; ho;=420800; fr=300MFu	SOT23,30D23	2007/00/2009
BE		DIODS	1	0.00		B·E·C
SE SE	2DC4617R		npn	V _{CB0} -60 B; I _C = 150 MA; P _D =150 MBT; h ₂₁ =180390; f _T =180 MFu	SOT523	
SE	DTC114TET1	MOT	Dnpn	V_{CB0} =50 B; I_C =100 mA; P_D =150 mBτ; h_{21} >100600; f_T >250 MΓμ; R_1 =10 κΩm	S0T416,SC75A	B.E.C
BE.	MMBZ5230B	VISH	dz	V _Z (I _{ZT} =20 мA)=4.464.94 B; I _R <5 мкА	SOT23,SOD23	A•n.c.•K
BE.	MMBZ5230BLT1	ON	dz	V ₂ (I _{ZT} =20 mA)=4.464.94 B; I _R <5 mxA	SOT23,SOD23	A•n.c.•K
BE.	MUN2215T1	ON	Dnpn	V _{CBO} =50B; I _C =100 MA; P _D =230 MBT; h ₂₁ >160; R ₁ 10 KOM	SOT346,SC59	B·E·C
BE	MUN5215T1	ON	Dnpn	V _{CB0} =50 B; I _C = 100 мА; P _D =200 мВт; h ₂₁ > 160; R ₁ 10 кОм	SOT323,SC70	B·E·C
BE	FMMTA92R	ZETEX	onp	V _{DB0} =300 B; I _C =200 мА; P _D =330 мВт; h ₂₁ >25; f _T >50 МГц	SOT23.SOD23	E-B-C
BEA	BC850A	FAIR	non	V _{CB0} =50 B; I _C =100 мА; P _D =310 мВт; h ₂₁ =110220; f _T =300 МГц	SOT23,SOD23	B·E·C
BEB	BC850B	FAIR	non	V _{CR0} =50 B; I _C = 100 мА; P _D =330 мВт; h ₂₁ =200450; f _T =300 МГц	SOT23.SOD23	
BEC	BC850C	FAIR	non	V _{CBD} =50B; I _C =100mA; P _D =330mBr; h ₂₁ =420800; f _T >300MFц	SOT23.SOD23	
BF.	2DC4617S	DIODS	non	V _{CR0} =60 B; I _C = 150 мA; P _D = 150 мBт; h _{O1} = 270560; f _T = 180 МГц	SOT523	B-E-C
BF	DTC143TET1	MOT	Dnpn	V _{CB0} = 50 B; I _C = 100 mA; P _D = 150 mBτ; h ₂₁ = 100600; f _T > 250 MΓu; R ₁ =4.7 κOm	SOT416,SC75A	
8F	MMBZ5231B	VISH	dz	V _A (I _m =20 MA)=4.845.36 B; I _B <5 MKA	SOT23 SOD23	A.n.a.k
or RF	MMBZ5231BLT1	ON	dz	V _X (I _{ZI} =20 MA)=4.845.36 B; I _R \ 5 MKA	SOT23,SOD23	
BF	MUN2216T1	ON	Dnpn	V _{CPO} =50B; I _C =100 mA; P _D =230 mB;; h _{Pl} >160; R ₁ 4.7 κOm	SOT346,SC59	
				000	5 55 5	
3F	MUN5216T1	ON	Dnpn	V _{CB0} =50 B; I _C = 100 MA; P _D =200 MBT; h ₂₁ > 160; R ₁ 4.7 KOM	SOT323,SC70	
BG.	FMMZ5232	ZETEX	dz	V _Z =5.6B; Z _{ZT} (I _Z =20mA)=11 0m	SOT23,SOD23	100000000000000000000000000000000000000
BG .	MMBZ5232B	VISH	dz	V _Z (I _{ZT} =20 mA)=5.325.88 B; I _R <5 mкA	SOT23,SOD23	
BG .	MMBZ5232BLT1	ON	dz	V _Z (I _{ZT} =20 mA)=5.325.88 B; I _R <5 mkA	SOT23,SOD23	
BG .	MUN2230T1	ON	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _D =230 mBT; h ₂₁ >3; 1 kOm/1 kOm	SOT346,SC59	
BG	MUN5230T1	ON	Dnpn	V _{CB0} =50 B; I _C =100 мA; P _D =200 мВт; h ₂₁ > 3; 1 кОм/1 кОм	SOT323,SC70	
BH	DTC123EET1	МОТ	Dnpn	V_{CB0} =50 B; I_C =100 mA; P_D =150 mBT; h_{21} >20; f_T >250 MF μ ; R_1/R_2 =2.2/2.2 kOm	S0T416,SC75A	B-E-C
3H	FMMZ5233	ZETEX	dz	V ₇ =6 B; Z ₇₇ (I ₇ =20 mA)=7 Om	SOT23,SOD23	A·n.c.·K
3H	MMBZ5233B	VISH	dz	V ₂ (I ₂₇ =20 mA)=5.706.30 B; I _B <5 mkA	SOT23.SOD23	A·n.c.·K
3H	MMBZ5233BLT1	ON	dz	V.(I ₂₇ =20 mA)=5.706.30 B; I ₆ <5 mkA	SOT23.SOD23	
BH	MUN2231T1	ON	Dnpn	V _{CPD} =50B; I _C =100 MA; P _D =230 MBT; h ₂₁ >8; 2.2 KOM/2.2 KOM	SOT346.SC59	
BH BH	MUN5231T1	ON	Dnpn	V _{CBD} =50B; I _C =100mA; P _D =200mBT; h ₂₁ >8; 2.2kOm/2.2kOm	SOT323,SC70	
BJ	DTC143EET1	MOT	Dnpn	V _{CBD} =50 B; I _C = 100 мA; P _D =150 мBτ; h ₂₁ > 20; f ₁ > 250 MFu; R ₂ ;R ₂ = 4.7/4.7 κOm	S0T416,SC75A	
BJ	FMMZ5234	ZETEX	dz	V ₂ =6.2B; Z ₂₇ {1 ₂ =20 MA}=7 OM	SOT23,SOD23	A+n.c.+K
BJ .	MMBZ5234B	VISH	dz	V ₂ (I ₂₇ =20 mA)=5.896.51 B; I _R <5 mkA	SOT23,SOD23	A·n.c.·K
3.J	MMBZ5234BLT1	ON	dz	V _A I ₂₇ =20 mA)=5.896.51 B; I _R <5 mkA	SOT23,SOD23	
SJ	MUN2232T1	ON	Dnon	V _{CRO} =50 B; I _C =100 MA; P _D =230 MBT; h ₂₁ >15; 4.7 KOM/4.7 KOM	SOT346.SC59	0.000
SJ	MUN5232T1	ON	Dnon	V _{CR0} =50B; I _C =100 MA; P _D =200 MBT; h ₂₁ >15; 4.7 KOM/4.7 KOM	SOT323.SC70	100000000
3K	DTC143ZET1	MOT	Dnon	V _{CB0} =50B; I _C =100mA; P _D =150mBr; h ₂₁ >80; f _T >250 MFu;	SOT416.SC75A	
at.	DISTAGLETT	WOI	Dilpil	R ₁ /R ₂ =4.7/47kOm	JOINTO, JOFUM	D L.0

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
BK	FMMZ5235	ZETEX	dz	V _z =6.8B; Z _{ZT} (I _z =20 MA)=5 OM	SOT23,SOD23	A·n.c.·K
3K	MMBZ5235B	VISH	dz	V ₂ (I _{2T} =20 mA)=6.467.14B; I _B <3 mKA	SOT23,SOD23	A·n.c.·K
BK	MMBZ5235BLT1	ON	dz	V ₂ (I _{2T} =20 mA)=6.467.14B; I _B <3 mkA	SOT23,SOD23	A·n.c.·K
BK	MUN2233T1	ON	Dnpn	V _{CRO} =50 B; I _C =100 mA; P _D =230 mBT; h ₂₁ > 80; 4.7 кOm/47 кOm	SOT346,SC59	B·E·C
BK	MUN5233T1	ON	Dnpn	V _{CB0} =50B; I _C =100 mA; P _D =200 mBT; h ₂₁ >80; 4.7 kOm/47 kOm	SOT323,SC70	B-E-C
8L	DTC124XET1	MOT	Dnpn	V _{CB0} =50 B; I _C =100 мА; P ₀ =150 мВт; h ₂₁ >68; f ₁ >250 МГц; R ₁ /R ₂ =22/47 кОм	SOT416,SC75A	B-E-C
8L	FMMZ5236	ZETEX	dz	V ₂ =7.5B; Z ₇₇ (I ₂ =20 mA)=6 Om	SOT23,SOD23	A·n.c.·K
8L	MMBZ5236B	VISH	dz	V ₂ (I ₇₇ =20 mA)=7.127.88 B; I _R <3 mkA	SOT23,SOD23	A·n.c.·K
8L	MMBZ5236BLT1	ON	dz	V ₂ (I _{2T} =20 mA)=7.127.88B, I _R <3 mkA	SOT23,SOD23	A·n.c.·K
BL	MUN2234T1	ON	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _D =230 mBr; h ₂₁ >80; 22 kOm/47 kOm	SOT346.SC59	B-E-C
8L	MUN5234T1	ON	Dnon	V _{CB0} =50 B; I _C =100 mA; P ₀ =200 mBt; h ₂₁ >80; 22 kOm/4.7 kOm	SOT323.SC70	
8M	DTC123JET1	MOT	Dnpn	V_{CB0} =50 B; I_C =100 xA; P_0 =150 xBt; h_{21} >80; f_T >250 MFu; R_T / R_p =2.2/47 xOx	SOT416,SC75A	B•E•C
BM	FMMZ5237	ZETEX	dz	V ₂ =8.2B; Z ₇₁ (I ₂ =20 mA)=8 Om	SOT23,SOD23	A·n.c.·K
BM	MMBZ5237B	VISH	dz	V ₂ (I _{2T} =20 mA)=7.798.61 B; I _B <3 m/sA	SOT23,SOD23	A·n.c.·K
BM	MMBZ5237BLT1	ON	dz	V ₂ (I _{2T} =20 mA)=7.798.61 B; I _B <3 mKA	SOT23,SOD23	A·n.c.·K
BM	MUN5235T1	ON	Dnpn	V _{CR0} =50B; I _C =100 mA; P _D =200 mBt; h ₂₁ >80; 2.2 kOm/4.7 kOm	SOT323,SC70	
BN	DTC115EET1	MOT	Dnpn	V _{C80} =50 B; I _{C(max)} = 100 mA; P _D = 150 mBτ; h ₂₁ > 82; f _T > 250 MΓu; R ₁ /R _p = 100/100 κOm	SOT416,SC75A	B•E•C
BN	FMMZ5238	ZETEX	dz	V ₂ =8.7 B; Z ₇₇ (I ₂ =20 mA)=8 Om	SOT23,SOD23	A·n.c.·K
BN	MMBZ5238B	VISH	dz	V ₂ (I ₇₇ =20 mA)=8.269.14B; I ₈ <3 mKA	SOT23,SOD23	A·n.c.·K
BN	MMBZ5238BLT1	ON	dz	V ₂ (I ₂₇ =20 mA)=8.269.14B; I _B <3 mKA	SOT23,SOD23	A·n.c.·K
BN	MUN2236T1	ON	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _D =230 mBr; h ₂₁ >80; 100 кОм/100 кОм	SOT346,SC59	B·E·C
BN	MUN5236T1	ON	Dnpn	V _{CB0} =50B; I _C =100 мA; P _D =200 мВт; h ₂₁ >80; 100 кОм/100 кОм	SOT323,SC70	B-E-C
BP	DTC144WET1	мот	Dnpn	V_{CS0} =50 B; $I_{C(ms)}$ =100 mA; P_0 =150 mBT; h_{21} >56; f_1 >250 MFu; R_1/R_2 =47/22 xOm	SOT416,SC75A	B-E-C
BP	FMMZ5239	ZETEX	dz	Vz=9.1B; Zzt(Iz=20 mA)=10 Om	SOT23,SOD23	A·n.c.·K
BP	MMBZ5239B	VISH	dz	V ₂ (I _{ZT} =20 mA)=8.659.56B; I _R <3 m/A	SOT23,SOD23	A·n.c.·K
BP	MMBZ5239BLT1	ON	dz	V ₂ (I _{ZT} =20 mA)=8.659.56 B; I _R < 3 mkA	SOT23,SOD23	A·n.c.·K
BP	MUN2237T1	ON	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _D =230 mBt; h ₂₁ >80; 41 kOm/22 kOm	SOT346,SC59	B·E·C
BP	MUN5237T1	ON	Dnpn	V _{CB0} =50 B; I _C =100 мA; P _D =200 мВт; h ₂₁ >80; 47 кОм/22 кОм	SOT323,SC70	B·E·C
BQ	FMMZ5240	ZETEX	dz	Vz=10B; Zzz(Iz=20mA)=17 Om	SOT23,SOD23	A·n.c.·K
BQ	MMBZ5240B	VISH	dz	V _z (I _{ZT} =20 mA)=9.510.5 B; I _R <3 mKA	SOT23,SOD23	A·n.c.·K
BQ	MMBZ5240BLT1	ON	dz	V ₂ (I _{ZT} =20 mA)=9.510.5 B; I _R <3 mkA	SOT23,SOD23	A·n.c.·K
BR	FMMZ5241	ZETEX	dz	V ₂ =11B; Z ₂₇ (I ₂ =20 mA)=22 Om	SOT23,SOD23	A·n.c.·K
BR	MMBZ5241B	VISH	dz	V ₂ (I _{ZT} =20 mA)=10.411.55B; I _B <2 m/sA	SOT23,SOD23	A·n.c.·K
BR	MMBZ5241BLT1	ON	dz	V ₂ (I _{ZT} =20 mA)=10.411.55B; I _R <2 m/sA	SOT23,SOD23	A·n.c.·K
BS	FMMZ5242	ZETEX	dz	V _z =12B; Z _{ZT} (I _z =20 mA)=30 Om	SOT23,SOD23	A·n.c.·K
BS	MMBZ5242B	VISH	dz	V ₂ (I _{ZT} =20 mA)=11.412.6B; I _R <1 mKA	SOT23,SOD23	A·n.c.·K
BS	MMBZ5242BLT1	ON	dz	V ₂ (I _{ZT} =20 MA)=11.412.6B; I _R <1 MKA	SOT23,SOD23	A·n.c.·K
BT	FMMZ5243	ZETEX	dz	V ₂ =13B; Z ₂₇ (I ₂ =9.5 MA)=13 OM	SOT23,SOD23	A·n.c.·K
BT	MMBZ5243B	VISH	dz	V ₂ (I _{ZT} =9.5 mA)=12.3513.65B; I _R <0.5 mkA	SOT23,SOD23	A·n.c.·K
BT.	MMBZ5243BLT1	ON	dz	V ₂ (I _{ZT} =9.5 mA)=12.3513.65B; I _B <0.5 mKA	SOT23,SOD23	A·n.c.·K
3T	MUN2240T1	ON	Dnpn	V _{CBO} =50B; I _G =100 mA; P _D =230 mBT; h ₂₁ > 160; R ₁ 47 kOm	SOT346,SC59	B·E·C
BU	FMMZ5244	ZETEX	dz	Vz=14B; Zz;(Iz=9mA)=15 Om	SOT23,SOD23	A·n.c.·K
BU	MMBZ5244B	VISH	dz	V ₂ (I _{ZT} =8.5 mA)=13.3014.70B; I _B <0.1 mkA	SOT23,SOD23	
3U	MMBZ5244BLT1	ON	dz	V ₂ (I ₂₇ =8.5 mA)=13.3014.70B; I _B <0.1 mkA	SOT23,SOD23	A·n.c.·K
3U	MUN2241T1	ON	Dnpn	V _{CBD} ; 50B; I _S : 100 mA; P _D : 230 mBr; h ₂₁ > 160; R ₁ 100 kOm	SOT346,SC59	
SV.	FMMZ5245	ZETEX	dz	V ₂ =15B; Z ₂₇ (I ₂ =8.5 mA)=16 Om	SOT23,SOD23	2000
SV.	MMBZ5245B	VISH	dz	V ₂ (I _{2T} =8.5 mA)=14.2515.75B; I _B <0.1 mKA	SOT23,SOD23	100000000000000000000000000000000000000
SV.	MMBZ5245BLT1	ON	dz	V ₂ (I _{2T} =8.5 mA)= 14.2515.75B; I _B <0.1 mkA	SOT23,SOD23	
3V2	PZM8.2NB	PHIL	dz	V _Z (I _{ZT} =5 mA)=7.768.64 B; Z _{ZT} (I _{ZT} =5 mA)<10 Om	SOT346,SC59	





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
8W	FMMZ5246	ZETEX	dz	Vz=16 B; Zz1(Iz=7.8 mA)=17 Om	SOT23,SOD23	A·n.c.·K
8W	MMBZ5246B	VISH	dz	V ₂ (I ₂₇ =7.8 mA)=15.216.8B; I _B <0.1 mkA	SOT23,SOD23	A·n.c.·K
8₩	MMBZ5246BLT1	ON	dz	V ₂ (I ₂₇ =7.8 mA)=15.216.8 B; I _R <0.1 mkA	SOT23,SOD23	A·n.c.·K
8X	FMMZ5247	ZETEX	dz	V ₂ =17 B; Z ₂₁ (I ₂ =7.4 mA)=19 Om	SOT23,SOD23	A+n.c.+K
8X	MMBZ5247B	VISH	dz	V ₂ (I ₂₇ =7.0 mA)=16.1517.85B; I _R <0.1 mKA	SOT23,SOD23	A·n.c.·K
8X	MMBZ5247BLT1	ON	dz	V _A (I ₂₇ =7.0 mA)=16.1517.85B; I _B <0.1 mKA	SOT23,SOD23	A·n.c.·K
8Y	FMMZ5248	ZETEX	dz	V ₂ =18B; Z ₇₁ (I ₂ =7 mA)=21 Om	SOT23,SOD23	A+n.c.+K
87	MMBZ5248B	VISH	dz	V ₇ (I ₇₇ =7.0 mA)=17.118.9 B; I _R <0.1 mrA	SOT23,SOD23	A·n.c.·K
8Y	MMBZ5248BLT1	ON	dz	V _A (I ₂₇ =7.0 mA)=17.118.9 B; I _B <0.1 mkA	SOT23.SOD23	A·n.c.·K
8Z	FMMZ5249	ZETEX	dz	V ₂ =19B; Z ₂₁ (I ₂ =6.6 mA)=23 Om	SOT23.SOD23	A·n.c.·K
8Z	MMBZ5249B	VISH	dz	V ₂ (I ₂₇ =6.2 mA)=18.0519.95B; I _B <01 mcA	SOT23,SOD23	A·n.c.·K
8Z	MMBZ5249BLT1	ON	dz	V _X (I _{ZT} =6.2 mA)=18.0519.95B; I _B <01 mcA	SOT23.SOD23	
8Z	TMPZ5249	ALLEG	dz	V _X (I _y =6.6 mA)=18.120.0B; I _L (V _R =14.0 B)<0.1 mkA; Z _{yy} (I _y =6.6 mA)<23 0m	S0T23,S0D23	A•n.c.•K
9.1X	02CZ9.1	TOSH	dz	V ₂ (I ₂₇ =5 mA)=8.509.60 B; I ₁ (V _B =7.0 B) < 0.5 mkA; Z ₂₇ (I ₂₇ =0.5 mA) < 120 Om	SOT346,SC59	A+n.c.+K
91A	FMMT591A	ZETEX	pnp	V _{CB0} =40 B; I _G = 1000 MA; P _D = 500 MBT; h ₂₁ = 300800; f _T > 150 MFц	SOT23,SOD23	
93	DTA143TE	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 MA; P_D =150 MBT; h_{21} =100600; f_T >250 MFu; P_1 =4.7 kOM	S0T416,SC75A	B·E·C
93	DTA143TKA	ROHM	Dpnp	V_{CB0} =50 B; I_{c} =100 mA; P_{D} =200 mBT; h_{21} =100600; f_{T} >250 MFu; P_{1} =4.7 kOm	S0T346,SC59	B·E·C
93	DTA143TUA	ROHM	Dpnp	V_{CB0} =50 B; $I_{\rm C}$ =100 mA; $P_{\rm D}$ =200 mBT; $h_{\rm 21}$ =100600; $f_{\rm T}$ >250 MFu; $R_{\rm 1}$ =4.7 kOm	S0T323,SC70	B•E•C
94	DTA114TE	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =150 mBT; h_{21} =100600; f_T >250 MFu; R_1 =10 kOm	SOT416,SC75A	B.E.C
94	DTA114TKA	ROHM	Dpnp	$V_{CB0}\text{=}50B;I_{C}\text{=}100\text{mA};P_{D}\text{=}200\text{mB}\text{T};h_{21}\text{=}100600;f_{T}\text{>}250\text{MFu};R_{1}\text{=}10\text{kOm}$	SOT346,SC59	B·E·C
94	DTA114TUA	ROHM	Dpnp	V_{CB0} =50 B; I_{C} =100 mA; P_{D} =200 mBr; h_{21} =100600; f_{T} >250 MFu; R_{1} =10 kOm		
94	DTC114TET1	MOT	Dnpn	V_{CB0} =50 B; I_{c} =100 мA; P_{D} =150 мBτ; h_{21} >100600; f_{T} >250 МГц; R_{1} =10 κOм	S0T416,SC75A	B·E·C
95	DTA124TE	ROHM	Dpnp	$ V_{CB0}\text{=}50B;I_{C}\text{=}100\text{mA};P_{D}\text{=}150\text{mB}\text{T};h_{21}\text{=}100600;f_{T}\text{>}250\text{MFu};R_{1}\text{=}22\text{kOm}$	SOT416,SC75A	B·E·C
95	DTA124TH	ROHM	Dpnp	V_{CB0} =50 B; I_{C} =100 mA; P_{D} =200 mBr; h_{21} =100600; f_{T} >250 MFu; R_{1} =22 kOm	SOT416,SC75A	B·E·C
95	DTA124TKA	ROHM	Dpnp	V_{CB0} =50 B; I_{C} =100 mA; P_{D} =200 mBT; h_{21} =100600; f_{T} >250 MFu; R_{1} =22 kOm	SOT346,SC59	B.E.C
95	DTA124TUA	ROHM	Dpnp	$V_{CB0}\text{=}50B;I_{C}\text{=}100\text{mA};P_{D}\text{=}200\text{mBT};h_{21}\text{=}100600;f_{T}\text{>}250\text{MFu};R_{1}\text{=}22\text{kOm}$	SOT323,SC70	B.E.C
96	DTA144TCA	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =150 mBt; h_{21} =100600; f_T >250 MFu; R_1 =47 kOm	SOT23,SOD23	B·E·C
96	DTA144TE	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =150 mBr; h_{21} =100600; f_T >250 MFu; R_1 =47 kOm	SOT416,SC75A	B·E·C
96	DTA144TKA	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBr; h_{21} =100600; f_T >250 MFu; R_1 =47 kOm	SOT346,SC59	B-E-C
96	DTA144TUA	ROHM	Dpnp	V _{CBO} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ =100600; f _T >250 MFu; R ₁ =47 kOm	SOT323,SC70	B·E·C
99	DTA115TE	ROHM	Dpnp	V_{CB0} =50 B; I_{c} =100 mA; P_{0} =150 mBT; h_{21} =100600; f_{T} >250 MFu; R_{1} =100 kOm	S0T416,SC75A	B·E·C
99	DTA115TKA	ROHM	Dpnp	V_{CB0} =50 B; I_{c} =100 mA; P_{D} =200 mBT; h_{21} =100600; f_{T} >250 MFU; R_{1} =100 kGM	SOT346,SC59	B-E-C
99	DTA115TUA	ROHM	Dpnp	V_{CB0} = 50 B; I_{c} = 100 mA; P_{D} = 200 mBT; h_{21} = 100600; f_{T} > 250 MFu; R_{1} = 100 kGM	S0T323,SC70	B·E·C
9A	DTA125TKA	ROHM	Dpnp	V_{CB0} =50 B; $I_{\rm C}$ =100 mA; $P_{\rm D}$ =200 mB τ ; h_{21} =100600; $f_{\rm T}$ >250 MFu; $R_{\rm 1}$ =200 kGm	SOT346,SC59	B·E·C
9A	DTA125TU	ROHM	Dpnp	V_{CB0} =50 B, I_{c} =100 mA; P_{D} =200 mBT; h_{21} =100600; f_{T} >250 MFu; P_{1} =200 kGM	S0T323,SC70	B·E·C
9A	FMMT2369AR	ZETEX	non	V _{CB0} =40 B; I _C =200 mA; P _D =330 mBT; h ₂₁ =40120	S0T23,S0D23	B·E·C
9A1	MMBZ9V1AL	ON	dz×2	V _Z (I _{ZT} =1 mA)=8.659.56B; V _E (I _E =10 mA)<0.9B	SOT23,SOD23	
9A1	PZM9.1NB2A	PHIL	dz×2	V _Z (I _{ZT} =5 mA)=8.859.23 B; Z _{Z1} (I _{ZT} =5 mA) < 10 Om	SOT346,SC59	K1 · K2 · A1, A2
9AA	BC856A	SAMS	pnp	V _{CB0} =80 B; I _C =100 мA; P _D =310 мВт; h ₂₁ =110220; f _T >150 МГц	SOT23,SOD23	B-E-C
9AB	BC856B	SAMS	pnp	V _{CB0} =80 B; I _C = 100 мA; P _D =310 мВт; h ₂₁ =200450; f _T > 150 МГц	SOT23,SOD23	B-E-C
9AC	BC856C	SAMS	pnp	V _{CB0} =80 B; I _C =100 мA; P _D =310 мВт; h ₂₁ =420800; f _T >150 МГц	SOT23,SOD23	B·E·C
9BA	BC857A	SAMS	pnp	V _{CB0} =50B; I _C =100 мA; P ₀ =310 мBт; h ₂₁ =110220; f _T >150 МГц	SOT23,SOD23	B·E·C
9BB	BC857B	SAMS	pnp	V _{CB0} =50 B; I _C = 100 мА; P _D =310 мВт; h ₂₁ =200450; f _T > 150 МГц	SOT23,SOD23	B·E·C
9BC	BC857C	SAMS	ono	V _{CR0} =50 B; I _C =100 mA; P _D =310 mBT; h ₂₁ =420800; f _T >150 MFц	SOT23 SOD23	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
9CA	BC858A	SAMS	pnp	V_{CB0} =30B; I_C =100 mA; P_D =310 mBt; h_{21} =110220; f_T >150 MFu	SOT23,SOD23	B-E-C
9CB	BC858B	SAMS	pnp	V_{C80} *30 B; I_C *100 mA; P_D *310 mBt; h_{21} *200450; f_T >150 M Γ_{IJ}	SOT23,SOD23	B-E-C
9CC	BC858C	SAMS	pnp	V_{C80} =30B; I_C =100 mA; P_0 =310 mBr; h_{21} =420800; f_T >150 M Γ_{IJ}	SOT23,SOD23	B-E-C
9DA	BC859A	SAMS	pnp	V _{G80} =30B; I _C =100 мA; P _D =310 мВт; h ₂₁ =110220; f _T >150 МГц	SOT23,SOD23	B-E-C
9DB	BC859B	SAMS	pnp	V_{C80} =30B; I_C =100 mA; P_D =310 mBT; h_{21} =200450; f_T >150 MFu	SOT23,SOD23	B-E-C
9DC	BC859C	SAMS	pnp	V_{C80} =30B; I_C =100 MA; P_D =310 MBT; h_{21} =420800; f_T >150 MFu	SOT23,SOD23	B-E-C
9EA	BC860A	SAMS	pnp	V_{C80} =50B; I_C =100 mA; P_D =310 mBr; h_{21} =110220; f_T >150 MFu	SOT23,SOD23	B-E-C
9EB	BC860B	SAMS	pnp	V _{сво} =50 B; I _с =100 мA; P _D =310 мВт; h ₂₁ =200450; f _T >150 МГц	SOT23,SOD23	B-E-C
9EC	BC860C	SAMS	pnp	V_{C80} =50B; I_C =100 MA; P_D =310 MBT; h_{21} =420800; f_T >150 MFu	SOT23,SOD23	B-E-C
9FA	BC807-16	SAMS	ono	V ₀₈₀ =50 B; I _C =800 мА; P _D =310 мВт; h ₂₁ =100250; f _T > 100 МГц	SOT23,SOD23	B-E-C
9FB	BC80725	SAMS	ono	V_{080} =50 B; I_0 =800 MA; P_0 =310 MBT; h_{21} =160400; f_T >100 MFL	SOT23,SOD23	B-E-C
9FC	BC807-40	SAMS	ono	V _{G80} =50 B; I _C =800 mA; P _D =310 mBt; h ₂₁ =250630; f _T > 100 MFu	SOT23,SOD23	B-E-C
9GA	BC808-16	SAMS	pnp	V _{CBB} =30B; I _C =800 мA; P _D =310 мВт; h ₂₁ =100250; f _T >100 МГц	SOT23.SOD23	12011311111111
9GB	BC808-25	SAMS	ono	V _{CB0} =30 B; I _C =800 mA; P _D =310 mBT; h ₂₁ =160400; f _T >100 MFu	SOT23.SOD23	100077 02
9GC	BC808-40	SAMS	ono	V _{CR0} =30 B; I _C =800 mA; P _D =310 mBT; h ₂₁ =250630; f _T >100 MFu	SOT23,SOD23	20-21-00
gp	BCX70HR	ZETEX	ngn	V _{CR0} =45 B; I _C =200 mA; P _D =330 mBt; h ₂₁ =180310; f _T >250 MFu	SOT23,SOD23	
9R	FMMT2369R	ZETEX	npn	V _{C80} =40 B; I _C =200 mA; P _D =330 mBr; h ₂₁ =40120	SOT23,SOD23	
9V1	PZM9.1NB	PHIL	dz	V ₂ (I _{2T} =5 mA)=8.569.55 B; Z _{2T} (I _{2T} =5 mA)<10 Om	SOT346.SC59	
Δ	IRLML2402	IR	nMOS	HEXFET; V _{DS} =20 B; I _D =0.9A; P _D =540 MBT; R _{DS(pt)} < 0.35 OM	SOT23,SOD23	6.5010.0010.0007
Λ	MRF947T1	MOT	npn	V _{C80} =20B; I _C =50мA; P _D =188мBт; h ₂₁ >50; f _T =8ГГц	SOT323.SC70	200000000000000000000000000000000000000
AO	HSMS2800	HP	shd	V _{BB} >70B; V _E (I _E =15 мA)<1.0B; I _E (V _B =50 B)<200 нA; C _D <2.0 пФ	SOT23.SOD23	3222 28
AO AO	HSMS280B	HP	shd	V _{BB} > 70 B; V _E (I _E =15 MA)<1.0 B; I _B (V _B =50 B)<200 HA; C _D <2.0 nΦ	SOT323.SC70	
A03	SST203	CALOG		V _{DS} =40 B; P _D =350 MBT; I _{DSS} =420 MA; Q _E =1.5 MCM	SOT23,SOD23	
A1	BAW56	ALLEG	d×2	55 50 500	SOT23,30D23	9
AI	DAVIOO	ALLEG	u×z	I_F <70 MA; V_{BR} >70 B; V_F (I_F =50 MA)<1.1 B; I_R <2500 HA; t_{RR} <6.0 HC; C_0 <2.0 πΦ	30123,30023	KI'KZ'AI,AZ
A1	BAW56	VISH	di×2	V_R <70 B; I_F <300 mA; V_F (I_F =150 mA)<1.25 B; I_R <5.0 mKA; C_0 <4.0 n Φ ; I_{RR} <6 Hc	SOT23,SOD23	K1-K2-A1,A2
A1	BAW56	ZETEX	di×2	V_R < 70 B; I_F < 100 mA; V_F (I_F = 50 mA) < 1.1 B; I_R < 2.5 mkA; C_D < 2.0 n Φ ; t_{PR} < 6 hc	SOT23,SOD23	K1·K2·A1,A2
A1	BAW56	FAIR	di×2	$V_R < 85 B$; $I_F < 200 \text{ mA}$; $V_F (I_F = 50 \text{ mA}) < 1 B$; $I_R < 2.5 \text{ mkA}$; $C_D < 2.0 \text{ m}\Phi$; $t_{RR} < 6 \text{ Hc}$	SOT23,SOD23	K1-K2-A1,A2
A1	BAW56W	PHIL	di×2	$V_R < 75 B$; $I_F < 150 \text{ mA}$; $V_F (I_F = 50 \text{ mA}) < 1.0 B$; $C_D < 2 \text{ n}\Phi$; $t_{RR} < 4 \text{ Hz}$	SOT323,SC70	K1-K2-A2,A1
A1	BAW56WT1	ON	di×2	V_R <70 B; I_F <200 mA; V_F (I_F =150 mA)<1.25 B; I_R <2 mkA; I_{PR} <4 Hc	SOT323,SC70	K1-K2-A1,A2
A1	HSMS2801	HP	shd	$V_{BR} > 70 \text{ B}; V_F (I_F = 15 \text{ mA}) \le 1.0 \text{ B}; I_R (V_R = 50 \text{ B}) \le 200 \text{ mA}; C_0 \le 2.0 \text{ m}$	SOT23,SOD23	n.c. · A·K
A11	MMBD1501A	NS	dl	$V_R < 180 \text{ B}; I_F < 600 \text{ mA}; V_F (I_F = 200 \text{ mA}) < 1.1 \text{ B}; C_D < 4 \text{ n} \Phi$	SOT23,SOD23	A·n.c.·K
A11	MMBD1501A	FAIR	dl	V _B < 200 B; I _F =200 mA; V _F (I _F =200 mA) < 1.1 B; C _D < 4 nΦ	SOT23,SOD23	A·n.c.·K
A13	MMBD1503A	NS	dl×2	V _B < 180 B; I _F < 600 mA; V _F (I _F = 200 mA) < 1.1 B; C _D < 4 πΦ	SOT23,SOD23	A1-K2-K1,A2
A13	MMBD1503A	FAIR	dk2	V _B <200 B; I _F =200 mA; V _F (I _F =200 mA)<1.1 B; C _D <4πΦ	SOT23,SOD23	A1-K2-K1,A2
A14	MMBD1504A	NS	dl×2	V _R <180 B; I _F <600 MA; V _F (I _F =200 MA)<1.1 B; C _D <4 nΦ	SOT23,SOD23	A1-A2-K1,K2
A14	MMBD1504A	FAIR	dl×2	V _B < 200 B; I _F = 200 mA; V _F (I _F = 200 mA) < 1.1 B; C _D < 4 nΦ	SOT23,SOD23	A1+A2+K1,K2
A15	MMBD1505A	NS	dl×2	V _B <180 B; I _E <600 mA; V _E (I _E =200 mA)<1.1 B; C _D <4 nΦ	SOT23,SOD23	K1-K2-A1,A2
A15	MMBD1505A	FAIR	dk2	V _R <200 B; I _F =200 mA; V _F (I _F =200 mA)<1.1 B; C _D <4nΦ	SOT23,SOD23	K1-K2-A1,A2
A16	ZC934A	ZETEX	var	V _B <12B; C ₀ (V _B =2.5B)=47.2557.75 nΦ; C _{1B} /C _{4B} <3.8; Q>80	SOT23,SOD23	A·n.c.·K
A17	ZC933A	ZETEX	ASL	V _B <12B; C ₀ (V _B =2.5B)=20.2524.75 πΦ; C _{1B} /C ₀ (4B)<3.5; Q>150	SOT23,SOD23	A·n.c.·K
Als	BAW56	INF	di×2	V _B <80 B; I _E <200 mA; V _E (I _E =150 mA)<1.25 B; C _D <2.0 πΦ; t _{BB} <4 hc	SOT23,SOD23	K1-K2-A1,A2
Als	BAW56T	INF	di×2	$V_R \le 80 B$; $I_F \le 200 \text{ mA}$; $V_F (I_F = 150 \text{ mA}) \le 1.25 B$; $C_D \le 2.0 \text{ n}\Phi$; $t_{RR} \le 4 \text{ Hc}$	SOT416,SC75A	
A1s	BAW56W	INF	di×2	V _R <80 B; I _F <200 mA; V _F (I _F =150 mA)<1.25 B; C ₀ <2.0 mΦ; t _{RR} <4 mc	SOT323,SC70	
A1t	BAW56T	PHIL	di×2	V _B <75B; I _E <150 mA; V _E (I _E =150 mA)<1.25B; t _{BB} <4 Hc	SOT416.SC75A	
A1X	MBAW56	MOT	di×2	V _R <70B; I _F <300 mA; V _F (I _F =150 mA)< 1.25B; I _R <5.0 mκA; C _D <4.0 nΦ; t _{an} <6 nC	SOT23,SOD23	100 00000000000000000000000000000000000
A2	BAS16T	DIODS	di	V _R <85 B; I _F <155 mA; V _F (I _F =150 mA)<1.25 B; I _R <2 mkA; t _{BR} <4 HC	SOT523	A·n.c.·K
A2	BAT18	SIEM	cpin	V _B <35B; I _E <100 mA; V _E (I _E =100 mA)<1.2 B; I _B <0.02 mκA; C _D <1.0 mΦ	SOT23,SOD23	100000000000000000000000000000000000000
A2	BAT18	PHIL	dtv	V _B <35B; I _E <100 мA; R _D <0.7 Ом; C _D <1.0 пФ	SOT23,SOD23	1.1.1000.000
A2	FMMD2836	ZETEX		V _R <75B; I _F <100мA; V _E (I _F =50мA)<1.0B; I _B <0.1 мкA; C ₀ <4.0 пФ; t _{RR} <6нс		





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
A2	HSMS2802	HP	shd×2	V _{BR} >70 B; V _E (I _F =15 mA)<1.0 B; I _B (V _B =50 B)<200 нA; C _D <2.0 пФ	SOT23,SOD23	A1 · K2 · K1,A2
42	HSMS280C	HP	shd×2	V _{BR} >70B; V _E (I _E =15 мA) < 1.0B; I _B (V _B =50 B) < 200 нА; С _D <2.0пФ	SOT323,SC70	A1 · K2 · K1, A2
A2	MMBD4148	VISH	di	V _B <75B; I _E <300 мА; V _E (I _E : 10 мА)<1.0 B; I _B <5.0 мкА; С _D <4 пФ; t _{BB} <6 нс	SOT23,SOD23	A·n.c.·K
A2s	BAT18	INF	cpin	V _B <35B; I _E <100 мA; V _E (I _E =100 мA)<1.2B; I _B <0.02 мкA; C _D <1.0 пФ	SOT23,SOD23	A+n.c.+K
A2X	MMBD2836LT1	МОТ	di×2	V _R <75B; I _F <100 mA; V _F (I _F : 50 mA)<1B; C _D <4 πΦ; t _{RR} <4 μc	SOT23,SOD23	K1 - K2 - A1 , A2
A3	1PS300	PHIL	fd×2	V _B <80B; I _E <200 mA; V _E (I _E :50 mA)<1.0 B; C _D <2.0 nΦ; t _{BB} <4hc	SOT323,SC70	K1-K2-A1,A2
A3	1SS181	TOSH	di×2	V _B <80B; I _E <100 mA; V _E (I _E : 100 mA)<1.2B; I _B <0.5 mkA; t _{BB} <4hc	SOT346,SC59	K1-K2-A1,A2
A3	1SS300	TOSH	di×2	V _B <80B; I _F <100 mA; V _F (I _F : 100 mA)<1.2B; t _{BB} <4hc	SOT323,SC70	K1-K2-A1,A2
A3	1SS360	TOSH	di×2	V _B <80B; I _E <100 mA; V _E (I _E =100 mA)<1.2B; I _B <0.5 mkA; t _{BB} <4hc	SOT416.SC75A	K1-K2-A1.A2
A3	1SS360F	TOSH	di×2	V _B < 80 B; I _E < 100 mA; V _E (I _E = 100 mA) < 1.2 B; I _B < 0.5 mkA; t _{BB} < 4 HC	SOT490,SC89	K1-K2-A1,A2
A3	HSMS2803	HP	shd×2	V _{BR} >70B; V _E (I _E =15 mA)<1.0B; I _B (V _B =50 B)<200 нA; C _D <2.0 πΦ	SOT23,SOD23	K1-K2-A1.A2
A3	HSMS280E	HP	shd×2	V _{BB} >70B; V _E (I _E =15 mA)<1.0B; I _B (V _B =50 B)<200 нA; C _D <2.0πΦ	SOT323.SC70	
A3	KDS120	KEC	di×2	V _B =80B; I _E =100 мA; I _B =0.5 мкА; С ₇ =2.2 пФ	S0T323.SC70	K1-K2-A1.A2
A3	MMBD1005LT1	мот	di×2	V _B <30B; I _F <200 mA; V _F (I _F =10 mA)<0.95 B	SOT23.SOD23	
A3	MMBD4448	VISH	fid	V _B <75B; I _F <500 mA; V _F (I _F =100 mA)<1.0 B; I _B <5.0 mkA; C _D <4 nΦ; t _{BB} <4 hc	SOT23.SOD23	
43o	BAT17	PHIL	shd	V _B <4B; I _E <30 мA; V _E I _E =1 мA)<450 мB; С _D <1 пФ	SOT23 SOD23	
A30	BAT17	PHIL	shd	V _R <4B; I _F <30 mA; V _F (I _F =1 mA)<450 mB; C _D <1 nΦ	SOT23.SOD23	A1·n.c.·K
A3t	BAT17	PHIL	shd	V _B <4B; I∈<30 mA; V _E (I _E =1 mA)<450 mB; C ₀ <1 mΦ	SOT23.SOD23	A1·n.c.·K
A3X	MMBD2835LT1	MOT	di×2	V _B <35B; I _E <100 mA; V _E (I _E =50 mA)<1B; C _D <4 nΦ; t _{BB} <4 Hc	SOT23.SOD23	100
A4	BAV70	ALLEG	di×2	I _E <100 MA; V _{BR} >70 B; V _E (I _E =10 MA)<0.86 B; I _R <5000 HA; t _{BR} <6.0 HC; C _D <1.5 πΦ	SOT23,SOD23	
A4	BAV70	VISH	di×2	$V_R < 70B$; $I_F < 300$ mA; $V_F (I_F = 150$ mA) < 1.25 B; $I_R < 5.0$ m kA; $C_D < 4$ n Φ ; $I_{BB} < 6$ HC.	SOT23,SOD23	A1+A2+K1,K2
44	BAV70	ZETEX	di×2	V _B <70B; I _E <100 мA; V _E (I _E =50 мA)<1.1B; I _B <5.0 мкA; C _D <1.5 пФ; t _{BB} <6 нс	SOT23,SOD23	A1-A2-K1,K2
44	BAV70	MCC	di×2	V _B <75B; I _E <150 мA; V _E (I _E =10 мA)<0.855 B; C _D <2 пФ; t _{BB} <4 нс	SOT23,SOD23	A1 - A2 - K1 K2
44	BAV70	Nat	di×2	V _B <70B; I _E <200 mA; V _E (I _E : 10 mA)<0.855 B; C _D <1.5 πΦ; t _{BB} <6 HC	SOT23,SOD23	A1-A2-K1,K2
44	BAV70	ZOWIE	di×2	V _B <70B; I _E <200 mA; V _E (I _E : 10 mA)<0.855 B; C _D <1.5 nΦ; t _{BB} <6 hc	SOT23,SOD23	A1 · A2 · K1 K2
A4	BAV70	PANJIT	di×2	V _B <75B; I _E <150 mA; V _E (I _E : 10 mA)<1B; C _D : 4 nΦ; t _{BB} <4 hc	SOT23,SOD23	A1 · A2 · K1 K2
A4	BAV70TT1	ON	di×2	V _B <70B; I _E <200 mA; V _E (I _E : 50 mA)<1B; C _D <1.5 nΦ; t _{BB} <6 hc	SOT416,SC75A	A1-A2-K1,K2
44	BAV70W	PHIL	di×2	V _B <70B; I _E <175 mA; V _E (I _E *50 mA)<1.0 B; C _D <1.5 nΦ; t _{BB} <4 HC	SOT323.SC70	A1-A2-K1,K2
44	HSMS2804	HP	shd×2	V _{PR} >70B; V _E (I _E =15 mA)<1.0B; I _R (V _R =50 B)<200 нA; C _D <2.0 пΦ	SOT23.SOD23	A1 · A2 · K1.K2
44	HSMS280F	HP	shd×2	V _{BR} >70B; V _E (I _E =15 мA)<1.0B; I _B (V _B =50 B)<200 нА; C _D <2.0пФ	SOT323.SC70	A1 • A2 • K1 . K2
A40	BAV70	PHIL	di×2	V _R <70B; I _F <215 mA; V _F (I _F =50 mA)<1.0 B; C _D <1.5 nΦ; t _{RR} <4Hc	SOT23.SOD23	
A4s	BAV70	INF	di×2	$\frac{V_{R} < 80B; I_{E} < 200\text{mA}; V_{E}(I_{E} = 50\text{mA}) < 1B; I_{R}(V_{R} = 70B) < 0.15\text{m/cA}; C_{D} < 1.5\text{n}\Phi; I_{BR} < 4\text{Hz}.}$	SOT23,SOD23	1-1100000000000000000000000000000000000
A4s	BAV70F	INF	di×2	$V_R < 80B; I_F < 200 \text{ mA}; V_F (I_F = 50 \text{ mA}) < 1B; I_R (V_R = 70B) < 0.15 \text{ m/s}; C_D < 1.5 \text{ n}\Phi; I_{BB} < 4 \text{ nc}$	TSFP-3,VESM	A1-A2-K1,K2
A4s	BAV70T	INF	di×2	$V_R < 80B; I_F < 200 \text{ MA}; V_F (I_F = 50 \text{ MA}) < 1B; I_R (V_R = 70B) < 0.15 \text{ MKA}; C_D < 1.5 \text{ n}\Phi; I_{BR} < 4 \text{ Hz}$	SOT416,SC75A	A1-A2-K1,K2
A4s	BAV70W	INF	di×2	V_R < 80 B; I_F < 200 mA; V_F (I_F = 50 mA) < 1 B; I_R (V_R = 70 B) < 0.15 m kA; C_D < 1.5 n Φ ; I_R < 4 Hc	S0T323,SC70	A1 • A2 • K1, K2
A4X	MBAV70	МОТ	di×2	V_R < 70 В; I_F < 300 мА; V_F (I_{F^*} 150 мА) < 1.25 В; I_R < 5.0 мкА; C_D < 4 л Φ ; I_{RR} < 6 нс	S0T23,S0D23	A1+A2+K1,K2
A5	FMMD2837	ZETEX	fid×2	$V_B < 35B$; $I_F < 100 \text{ mA}$; $V_F (I_F = 50 \text{ mA}) < 1.0B$; $I_B < 0.1 \text{ mcA}$; $C_D < 4.0 \text{ n}\Phi$; $t_{BB} < 6 \text{ hc}$	SOT23,SOD23	A1-A2-K1,K2
A5	MMBD2837LT1	МОТ	di×2	$V_R \le 30B$; $I_F \le 150 \text{ mA}$; $V_F (I_F = 50 \text{ mA}) \le 1B$; $C_D \le 4 \text{ n}\Phi$; $t_{RR} \le 4 \text{ Hz}$	SOT23,SOD23	A1-A2-K1,K2
A5p	BPY61	PHIL	pnpn	V _{GA} =70 B; I _A =175 mA; P _D =250 mBr; t _R <80 Hc	SOT23,SOD23	A·K·G
A5t	BRY61	PHIL	pnpn	V _{GA} =70 B; I _A =175 mA; P _D =250 mBr; t _B <80 hc	SOT23,SOD23	A·K·G
A6	BAS16	ALLEG	di	$I_{\rm F}$ < 600 MA; $V_{\rm BR}$ > 75 B; $V_{\rm F}$ ($I_{\rm F}$ = 1 mA) < 0.72 B; $I_{\rm R}$ < 1000 mA; $t_{\rm RR}$ < 6.0 mc; $C_{\rm O}$ < 2.0 n Φ	SOT23,SOD23	A•n.c.•K
A6	BAS16	FAIR	di	$V_R < 85B$, $I_F < 200$ mA; $V_F (I_F = 150$ mA) < 1.25 B; $I_R < 1.0$ m kA; $C_D < 2.0$ n Φ ; $I_{BR} < 6$ Hz.	SOT23,SOD23	A•n.c.•K
A6	BAS16	DIOT	di	$V_R < 85B$; $I_E < 200$ mA; $V_E (I_E = 150$ mA) < 1.25 B; $I_R < 1.0$ m kA; $C_D < 2.0$ n Φ ; $I_{BB} < 6$ Hz.	SOT23,SOD23	A•n.c.•K
A6	BAS16	ZETEX	di	$V_R < 75B$; $I_F < 250 \text{ mA}$; $V_F (I_F = 50 \text{ mA}) < 1.0B$; $I_R < 1.0 \text{ m/sA}$; $C_D < 2.0 \text{ n}\Phi$; $t_{RR} < 6 \text{ hc}$	SOT23.SOD23	A·n.c.·K

SOT490 TESM VMT3 1 SOT523 SOT323 SOT23-3 1 SOT523 SOT324 SOD23-3 1 SOT523 SOT346 SOD23-3 1 SOT523 SOT523 SOT525 SO

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
A6	BAS16	VISH	fid	V_R < 75B; I_F < 500 mA; V_F (I_F = 150 mA) < 1.25B; I_R < 1.0 mxA; C_D < 4.0 n Φ ; I_R < 4 mc.	SOT23,SOD23	A·n.c.·K
46	BAS16	PANJIT	di	$V_R < 75B$; $I_F < 250 \text{ mA}$; $V_F (I_F = 10 \text{ mA}) < 0.855B$; $I_R < 1 \text{ mKA}$; $C_D < 2 \text{ n}\Phi$; $t_{RR} < 6 \text{ HC}$	SOT23,SOD23	A·n.c.·K
46	BAS16T	PHIL	di	V_R < 75 B; I_F < 155 mA; V_F (I_F = 150 mA) < 1.25 B; I_R < 50 mrA; C_0 < 1.5 n Φ ; t_{RR} < 4 Hc	SOT416,SC75A	A•n.c.•K
46	BAS16TT1	ON	di	V _R <75B; I _E <200 mA; V _E (I _E =150 mA)<1.25B; I _R <1 mKA; t _{RR} <6 HC	SOT416,SC75A	A·n.c.·K
46	BAS16W	PANJIT	di	$V_R < 75B$; $I_F < 250 \text{ mA}$; $V_F (I_F = 10 \text{ mA}) < 0.855B$; $I_R < 1 \text{ mrA}$; $C_D < 2 \text{ n}\Phi$; $t_{RR} < 6 \text{ Hc}$	SOT323,SC70	A·n.c.·K
46	BAS16W	PHIL	di	$V_R < 75B$; $I_F < 175 \text{ mA}$; $V_F (I_F = 50 \text{ mA}) < 1.0 B$; $C_D < 1.5 \text{ n}\Phi$; $t_{RR} < 4 \text{ HC}$	SOT323,SC70	A·n.c.·K
46A	MMUN2111LT1	ON	Dpnp	V _{CBO} =50B; I _C =100 mA; P _D =246 mBT; h ₂₁ >35; 10 kOm/10 kOm	SOT23,SOD23	B-E-C
46B	MMUN2112LT1	ON	Dpnp	V _{CBO} =50 B; I _C =100 mA; P _D =246 mBT; h ₂₁ >60; 22 kOm/22 kOm	SOT23,SOD23	B-E-C
46C	MMUN2113LT1	ON	Dpnp	V _{CBO} =50 B; I _C =100 mA; P _D =246 mBt; h ₂₁ >80; 47 kOm/47 kOm	SOT23,SOD23	B-E-C
46D	MMUN2114LT1	ON	Dpnp	V _{CBO} =50 B; I _C =100 mA; P _D =246 mBr; h ₂₁ > 80; 100 кОм/100 кОм	SOT23,SOD23	B-E-C
A6E	MMUN2115LT1	ON	Dpnp	V _{OBO} =50 B; I _C =100 мA; P _D =246 мВт; h ₂₁ > 160; R ₁ 10 кОм	SOT23,SOD23	B-E-C
A6F	MMUN2116LT1	ON	Dpnp	V _{CBO} =50B; I _C =100mA; P _D =246 mBt; h ₂₁ >160; R ₁ 4.7 kOm	SOT23,SOD23	B-E-C
46G	MMUN2130LT1	ON	Dpnp	V _{CBO} =50 B; I _C =100 mA; P _D =246 mBr; h ₂₁ >3; 1 kOm/1 kOm	SOT23,SOD23	B-E-C
H6A	MMUN2131LT1	ON	Dpnp	V _{CBO} =50B; I _C =100mA; P _D =246 mBt; h ₂₁ >8; 2.2 kOm/2.2 kOm	SOT23,SOD23	B-E-C
A6J	MMUN2132LT1	ON	Dpnp	V _{CBO} =50 B; I _C =100 mA; P _D =246 mBT; h ₂₁ > 15; 4.7 кOm/4.7 кOm	SOT23,SOD23	B-E-C
46K	MMUN2133LT1	ON	Dpnp	V _{CBO} =50 B; I _C = 100 мА; P _D =246 мВт; h ₂₁ > 80; 4.7 кОм/47 кОм	SOT23,SOD23	B-E-C
46L	MMUN2134LT1	ON	Dono	V _{CBO} =50 B; I _C =100 mA; P _D =246 mBT; h ₂₁ > 80; 22 kOm/47 kOm	SOT23,SOD23	B·E·C
A60	BAS16	PHIL	fd	V _B <75B; I _E <215mA; V _E (I _E =50 mA)<1.0B; C _D <1.5 mΦ; t _{BB} <4Hc	SOT23,SOD23	A·n.c.·K
46s	BAS16	SIEM	di	$V_B < 75B$; $I_E < 250 \text{ mA}$; $V_E (I_E = 50 \text{ mA}) < 1.0B$; $I_B < 1.0 \text{ mKA}$; $C_D < 2.0 \text{ n}\Phi$; $t_{BB} < 6 \text{ hc}$	SOT23,SOD23	A·n.c.·K
46s	BAS16	INF	di	V _R <80 B; I _E <250 mA; V _E (I _E =150 mA)<1.25 B; I _R <50 mKA	SOT23,SOD23	
46s	BAS16W	INF	di	Vo < 80 B; Ic < 250 mA; Vc(Ic=150 mA) < 1.25 B; Io < 50 mkA	SOT323.SC70	A·n.c.·K
A7	BAV99	ALLEG	di×2	$I_{\rm F}$ <70 MA; $V_{\rm BR}$ >70 B; $V_{\rm F}(I_{\rm F}$ =50 MA)<1.1 B; $I_{\rm R}$ <2500 HA; $t_{\rm RR}$ <6.0 Hc; $C_{\rm n}$ <2.0 H Φ	SOT23,SOD23	A1 · K2 · K1,A2
A7	BAV99	VISH	di×2	$V_R < 70B$; $I_F < 300$ mA; $V_F (I_F = 150$ mA) $< 1.25B$; $I_R < 5.0$ mKA; $C_0 < 4.0$ n Φ ; $t_{BB} < 6$ mC.	SOT23,SOD23	A1-K2-K1,A2
A7	BAV99	ZETEX	di×2	V _B <70B; I _E <100mA; V _E (I _E =50mA)<1.1B; I _B <2.5mkA; C _D <1.5nΦ; t _{BB} <6hc	SOT23,SOD23	A1 · K2 · K1, A2
47	BAV99	DIOT	di×2	V _B <70 B; I _E <200 mA; V _E (I _E =150 mA)<1.25 B; I _B <2 mkA; t _{BB} <4 Hc	SOT23,SOD23	A1-K2-K1,A
A7	BAV99	ZOWIE	di×2	V _B <70 B; I _E <200 mA; V _E (I _E =150 mA)<1.25 B; I _B <2 mkA; t _{BB} <4 Hc	SOT23,SOD23	A1-K2-K1,A
A7	BAV99	MCC	di×2	V _R < 75 B; I _F < 150 mA; V _F (I _F =150 mA) < 1.25 B; I _R < 2.5 mkA; t _{RR} < 4 HC	SOT23,SOD23	A1-K2-K1,A
A7	BAV99	Nat	di×2	V _B < 70 B; I _E < 200 mA; V _E (I _E = 150 mA) < 1.25 B; t _{BB} < 6 Hc	SOT23,SOD23	A1-K2-K1,A
17	BAV99	JGD	di×2	V _R <75B; I _F <300 mA; V _F (I _F =150 mA)<1.25B; I _R <2 mKA; t _{RR} <4 HC	SOT23,SOD23	A1-K2-K1.A
47	BAV99W	DIOT	dix2	V _R <70 B; I _F <200 mA; V _F (I _F =150 mA)<1.25 B; I _R <2 mkA; t _{RR} <4 Hc	SOT323.SC70	
47	BAV99W	PHIL	fd×2	V _B <75B; I _E <150 mA; V _E (I _E =50 mA)<1.0 B; C _D <1.S5 nΦ; t _{BB} <4 hc	SOT323.SC70	A1-K2-K1.A2
47	BAV99WT1	ON	di×2	V _B <70 B; I _E <215 mA; V _E (I _E =150 mA)<1.25 B; I _B <2 mKA; t _{BB} <4 Hc	SOT323.SC70	A1-K1 A2-K2
47	DAN217U	ROHM	di×2	V _B < 80 B; I _E < 100 mA; P _D < 200 mBT; V _E (I _E : 100 mA) < 1.2 B	SOT323,SC70	A1-K2-K1.A2
47p	BAV99	PHIL	di×2	V _B <75B; I _F <215 mA; V _F (I _F =50 mA)<1.0 B; C _D <1.5 πΦ; t _{BB} <4 Hc	SOT23,SOD23	
A7s	BAV99	INF	di×2	V _R <80 B; I _F <200 мA; V _F (I _F =150 мA)<1.25 B; I _R <0.15 мкA; C _D <1.5 пФ; t _{RR} <4 нс	SOT23,SOD23	
A7s	BAV99F	INF	di×2	V_R < 80 B; I_F < 200 mA; V_F (I_F = 150 mA) < 1.25 B; I_R < 0.15 mkA; C_0 < 1.5 n Φ ; I_{RR} < 4 Hc	TSFP-3,VESM	A1-K2-K1,A2
A7s	BAV99T	INF	di×2	V_R < 80 B; I_F < 200 mA; V_F (I_F = 150 mA) < 1.25 B; I_R < 0.15 mkA; C_0 < 1.5 n Φ ; I_R < 4 mc	SOT416,SC75A	A1-K2-K1,A2
A7s	BAV99W	INF	di×2	V_R < 80 B; I_F < 200 mA; V_R (I_F = 150 mA) < 1.25 B; I_R < 0.15 mkA; C_D < 1.5 πΦ; I_{RR} < 4 HC	SOT323,SC70	
48	BAS19	ALLEG	d	$I_{F}<200\text{mA}; V_{BR}>100\text{B}; V_{F}I_{F}=200\text{mA})<1.25\text{B}; I_{R}<100\text{mA}; t_{RR}<50\text{hc}; C_{O}<5.0\text{n}$	SOT23,SOD23	
A8	BAS19	PANJIT	di	$V_R \le 100 B; I_F \le 200 mA; V_F (I_F = 100 mA) \le 1.0 B; I_R \le 0.1 mkA; C_D \le 2 n\Phi; t_{RR} \le 50 Hc$	SOT23,SOD23	A·n.c.·K
A8	BAS19	JGD	di	$V_R \le 100 B; I_F \le 200 \text{mA}; V_F (I_F = 100 \text{mA}) \le 1.0 B; I_R \le 0.1 \text{mxA}; C_D \le 2 n \Phi; t_{nR} \le 50 \text{Hz}$	SOT23,SOD23	
48	BAS19	VISH	di	V_R < 100 B; I_F < 400 mA; V_F (I_F = 200 mA) < 1.25 B; I_R < 0.1 mrA; C_0 < 5.0 n Φ ; t_{RR} < 50 Hc	SOT23,SOD23	A·n.c.·K





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
A8	BAS19	ZETEX	di	V_R <100 B; I_F <200 мA; V_F (I_F =100 мA)<1.0 B; I_R <0.1 мкA; C_D <5.0 πΦ; I_{RR} <50 нс	SOT23,SOD23	A•n.c.•K
A8	BAS19W	PANJIT	di	$V_R \le 100 \text{ B; } I_F \le 200 \text{ MA; } V_F (I_F = 100 \text{ MA}) \le 1.0 \text{ B; } I_R \le 0.1 \text{ M/KA; } C_D \le 2 \text{ m} \Phi; \\ I_{BB} \le 50 \text{ Hz}$	SOT323,SC70	A•n.c.•K
48	SI2308DS	VISH	nMOS	V _{DS} =60B; I _D =1.6 A; P _D =800 mBr; R _{DSlott} < 0.22 Om	SOT23,SOD23	G·S·D
A80	BAS20	PANJIT	di	$V_R \le 150 \text{ B; } I_F \le 200 \text{ mA; } V_F (I_F = 100 \text{ mA}) \le 1.0 \text{ B; } I_R \le 0.1 \text{ m/sA; } C_D \le 1.5 \text{ n}\Phi; \\ I_{BB} \le 50 \text{ Hz}$	SOT23,SOD23	A•n.c.•K
A80	BAS20W	PANJIT	di	$V_R \le 150 \text{ B; } I_F \le 200 \text{ mA; } V_F (I_F = 100 \text{ mA}) \le 1.0 \text{ B; } I_R \le 0.1 \text{ m/sA; } C_0 \le 1.5 \text{ n}\Phi; I_{BR} \le 50 \text{ Hz}$	SOT323,SC70	A+n.c.+K
A81	BAS20	JGD	di	$V_R < 150 \text{ B; } I_F < 200 \text{ mA; } V_F (I_F = 100 \text{ mA}) < 1.0 \text{ B; } I_R < 0.1 \text{ m/A; } C_0 < 1.5 \text{ n}\Phi; \\ I_{BR} < 50 \text{ Hz}$	SOT23,SOD23	A•n.c.•K
A81	BAS20	VISH	di	$V_R <$ 150 B; $I_F <$ 400 mA; $V_F (I_F =$ 200 mA) < 1.25 B; $I_R <$ 0.1 mrA; $C_0 <$ 5.0 n Φ ; $I_{BB} <$ 50 Hc	SOT23,SOD23	A•n.c.•K
A81	BAS20	ZETEX	di	$V_R < 150 \text{ B; } I_F < 200 \text{ mA; } V_F (I_F = 100 \text{ mA}) < 1.0 \text{ B; } I_R < 0.1 \text{ m/A; } C_D < 5.0 \text{ n}\Phi; \\ I_{BB} < 50 \text{ Hz}$	SOT23,SOD23	A•n.c.•K
A82	BAS21	ALLEG	di	I_{e} < 200 mA; V_{BR} > 200 B; $V_{e}(I_{e}$ = 100 mA) < 1.0 B; I_{R} < 100 hA; I_{BR} < 50 hc; C_{O} < 5.0 n Φ	SOT23,SOD23	A+n.c.+K
482	BAS21	PANJIT	di	V_R <200 B; I_e <200 mA; V_E (I_e =100 mA)<1.0 B; I_R <0.1 mrA; C_0 <1.5 n Φ ; I_{BR} <50 Hc	SOT23,SOD23	A•n.c.•K
A82	BAS21	VISH	di	V_R < 200 B; I_F < 400 mA; V_F (I_F = 200 mA) < 1.25 B; I_R < 0.1 mrA; C_0 < 5.0 n Φ ; t_{RR} < 50 Hz	SOT23,SOD23	A•n.c.•K
A82	BAS21	ZETEX	di	V_R < 200 В; I_F < 200 мА; V_F (I_F = 100 мА) < 1.0 В; I_R < 0.1 мкА; C_D < 5.0 п Φ ; I_{RR} < 50 нс	SOT23,SOD23	A•n.c.•K
A82	BAS21W	PANJIT	di	$V_R < 200 \text{ B; } I_F < 200 \text{ mA; } V_F (I_F = 100 \text{ mA}) < 1.0 \text{ B; } I_R < 0.1 \text{ m/A; } C_0 \le 1.5 \text{ n}\Phi; \\ I_{RR} \le 50 \text{ Hz}$	SOT323,SC70	A•n.c.•K
A82	CMPD2003	CSI	di	I_F <250 MA; V_R =200 B; V_R (I_F =100 MA)<1.0 B; I_R <100 HA; t_{RR} <50 HC; C_T <5.0 n Φ	SOT23,SOD23	A•n.c.•K
A8A	MMUN2211LT1	ON	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ > 35; 10 kOm/10 kOm	SOT23,SOD23	B·E·C
A8B	MMUN2212LT1	ON	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _O =200 mBT; h ₂₁ >60; 22 kOm/22 kOm	SOT23,SOD23	B·E·C
A8C	MMUN2213LT1	ON	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >80; 47 kOm/47 kOm	SOT23,SOD23	B·E·C
A8D	MMUN2214LT1	ON	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >80; 100 kOm/100 kOm	SOT23,SOD23	B·E·C
A8E	MMUN2215LT1	ON	Dnpn	V _{CBO} = 50 B; I _C = 100 мA; P _D = 200 мВт; h ₂₁ > 160; R ₁ 10 кОм	SOT23,SOD23	B·E·C
A8F	MMUN2216LT1	ON	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ > 160; R ₁ 4.7 kOm	SOT23,SOD23	B·E·C
A8G	MMUN2230LT1	ON	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >3; 1 kOm/1 kOm	SOT23,SOD23	B·E·C
H8A	MMUN2231LT1	ON	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >8; 2.2 kOm/2.2 kOm	SOT23,SOD23	B·E·C
A8J	MMUN2232LT1	ON	Dnpn	V _{CBO} =50 B; I _C =100 мA; P _D =200 мВт; h ₂₁ >15; 4.7 кОм/4.7 кОм	SOT23,SOD23	B·E·C
A8K	MMUN2233LT1	ON	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ > 80; 4.7 κOm/47 κOm	SOT23,SOD23	B·E·C
A8L	MMUN2234LT1	ON	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >80; 22 kOm/47 kOm	SOT23,SOD23	B·E·C
A8R	MMUN2238LT1	ON	Dnpn	V _{CBD} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ > 160; R ₁ 2.2 kOm	SOT23,SOD23	B·E·C
U8A	MMUN2241LT1	ON	Dnpn	V _{CBO} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ > 160; R ₁ 100 кОм	SOT23,SOD23	B·E·C
A9	1SS294	TOSH	shd	V _B >40B; V _E (I _F =100 мA) < 0.6 B; I _B (V _B =40 B) < 5 мкА; С _Т < 25 пФ	SOT346,SC59	A+n.c.+K
A9	1SS322	TOSH	shd	V _R <40B; I _F <100 mA; V _F (I _F =100 mA)<0.6B; C _D =18 mΦ	SOT323,SC70	A+n.c.+K
A9	FMMD2835	ZETEX	fid×2	$V_B < 35B$; $I_E < 100 \text{ mA}$; $V_E (I_E = 50 \text{ mA}) < 1.0B$; $I_B < 0.1 \text{ m/sA}$; $C_D < 4.0 \text{ m}\Phi$; $t_{BB} < 6 \text{ hc}$	SOT23,SOD23	K1 · K2 · A1, A2
49	SI2309DS	VISH	pMOS	V _{DS} =60B; I _D =0.85 A; P _D =800 mBT; R _{DS(on)} <0.55 Om	SOT23,SOD23	G·S·D
A91	BAS17	PHIL	dz	V _B <5B; I _E <200 мA; V _E (I _E =100 мА)<0.96B; I _B <5 мкА; C _D <140 пФ	SOT23,SOD23	A+n.c.+K
AA	BCW60A	ALLEG	non	V _{CB0} =32B; I _{CB0} <20 HA; h ₂₁ =120220; V _{CB1sati} <0.35B; f _T >125MFu	SOT23,SOD23	B·E·C
AA	BCW60A	CDIL	npn	V _{CB0} =32B; I _C =200 мА; P _D =250 мВт; h ₂₁ =120220; f _T >100МГц	SOT23,SOD23	B·E·C
AA	BCW60A	SAMS	npn	V _{CR0} =32B; I _C =100 мA; P _D =350 мВт; h _{D1} =120220; f _T >125МГц	SOT23,SOD23	B·E·C
AA	BCW60A	ZETEX	npn	V _{CR0} =32B; I _C =200mA; P _D =330mBT; h ₂₁ =120220; f _T >250MFu	SOT23,SOD23	B·E·C
AAA	MAX6806XR46	MAX	vd	V _{тВ} =4.6B; V _{DD} =1.25.5 B; I _{DE} <80 мкА	SOT323,SC70	200000000000000000000000000000000000000
АДА	MMBF4856LT1	MOT	nFET	V _{DS} =40 B; I _{DSS} =50 MA; P _D =225 MBr	SOT23,SOD23	-
AAAA	MAX809LUR	MAX	mrc	V _{тв} =4.63 В; V _{пп} =1.25.5 В; I _{сс} <100 мкА	SOT23,SOD23	GND-RST-V
AAB	MAX6806XR26	MAX	vd	V _{тв} =2.6B; V _{пп} =1.25.5 B; I _{сс} < 80 мкА	SOT323,SC70	
AAC	MAX6806XR23	MAX	vd	V _{TR} =2.3B; V _{DD} =1.25.5B; I _{DC} <80 мкA	SOT323,SC70	
AAD	CMPD4448	CSI	dih	$I_{F}=250 \text{ MA}; V_{B}=75 \text{ B}; V_{F}(I_{F}=100 \text{ MA}) < 1.0 \text{ B}; I_{B} < 25 \text{ HA}; I_{BB} < 4.0 \text{ Hc}; C_{T} < 4.0 \text{ n}\Phi$		

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
AAD	MAX6807XR46	MAX	٧d	V _{TB} =4.6B; V _{DD} =1.25.5B; I _{DD} <80 mKA	SOT323,SC70	RST · GND · V _{CC}
AAD	TMPD4448	ALLEG	d	$I_F\!<\!600\text{mA},V_{BR}\!>\!100\text{B},V_F\!\{I_F\!=\!100\text{mA}\}\!<\!1.0\text{B};I_R\!<\!25\text{HA};t_{BR}\!<\!4.0\text{HC};}$ $C_0\!<\!4.0\text{n}\Phi$	SOT23,SOD23	A·n.c.·K
AAE	MAX6807XR26	MAX	٧d	V _{TR} =2.6B; V _{DD} =1.25.5B; I _{CC} <80 мкА	SOT323,SC70	RST · GND · V _{CC}
AAF	MAX6808XR46	MAX	vd	V _{TR} =4.6B; V _{DD} =1.25.5B; I _{CC} <80 мкА	SOT323,SC70	RST · GND · V _{CC}
AAG	MAX6808XR26	MAX	vd	V _{TR} =2.6B; V _{DD} =1.25.5B; I _{CC} <80 мкА	SOT323,SC70	RST • GND • V _{CC}
AAG	MMBR951ALT1	MOT	npn	V_{CB0} =20 B; I_C =100 mA; P_0 =322 mBt; h_{21} =75150; f_T =8000 MF μ	SOT23,SOD23	
AAH	MAX6326XP22	MAX	mrc	V _{TR} =2.2B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA	SOT323,SC70	
AAI	MAX6327XR22	MAX	mrc	V _{TR} =2.2B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA	SOT323,SC70	GND · RST · V _{CC}
LAA	MAX6328XR22	MAX	mrc	V _{TR} =2.2B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA	SOT323,SC70	GND · RST · V _{CC}
AAN	MAX809LXR	MAX	mrc	V _{TR} =4.63B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{CC}
AAO	MAX809MXR	MAX	mrc	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{CC}
AAp	BCW60A	PHIL	npn	V_{CB0} =32B; I_C =200 mA; P_D =250 mBT; h_{21} =120220; f_T >100 MFu	SOT23,SOD23	B-E-C
AAP	MAX809TXP	MAX	mrc	V _{TB} =3.08B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{CC}
AAQ	2SD1757KQ	ROHM	npn	V_{CB0} =30 B; I_C =500 mA; P_D =200 mBr; h_{21} =120270; f_T >150 M Γ_{LL}	SOT346,SC59	B-E-C
AAQ	MAX809SXR	MAX	mrc	V _{TR} =2.93B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{GC}
AAR	2SD1757KR	ROHM	npn	V_{CB0} =30 B; I_C =500 mA; P_D =200 mBt; h_{21} =180390; f_T >150 MFu	SOT346,SC59	B-E-C
AAR	MAX809RXR	MAX	mrc	V _{TR} =2.63B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{GG}
AAR	TMPD4153	ALLEG	d	I_F <600 mA; V_{BR} >75 B; $V_f(I_F$ =1 mA)<0.67 B; I_R <50 mA; t_{BR} <4.0 nc; C_0 <4.0 n Φ	SOT23,SOD23	A·n.c.·K
AAS	2SD1757KS	ROHM	npn	V _{CB0} =30 B; I _C =500 мA; P _D =200 мBт; h ₂₁ =270560; f _T >150 МГц	SOT346,SC59	B-E-C
AAs	BCW60A	SIEM	npn	V _{CB0} =32 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =120220; f _T =250 МГц	SOT23,SOD23	B-E-C
AAS	MAX809ZXR	MAX	mrc	V _{TR} =2.32B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{CC}
AAT	MAX810LXR	MAX	mrc	V _{TR} =4.63B; V _{DD} =1.25.5B; I _{CC} <60 MKA	SOT323,SC70	GND · RST · V _{CC}
AAU	MAX810MXR	MAX	mrc	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{CC}
AAV	MAX810TXR	MAX	mrc	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{CC}
WAA	MAX810RXR	MAX	mrc	V _{TR} =2.63B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{GC}
AAX	MAX810SXR	MAX	mrc	V _{TR} =2.93B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{CC}
AAY	MAX810ZXR	MAX	mrc	V _{TR} =2.32B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{CC}
AAZ	MAX803LXR	MAX	mrc	V _{TR} =4.63B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{CC}
AB	BCW60B	ALLEG	npn	V _{CB0} =32B; I _{CB0} <20 нА; h ₂₁ =180310; V _{CE(sat)} <0.35B; f _T >125 МГц	SOT23,SOD23	B-E-C
AB	BCW60B	CDIL	npn	V _{CB0} =32 B; I _C =200 мА; P _D =250 мВт; h ₂₁ =180320; f _T >100 МГц	SOT23,SOD23	B-E-C
AB	BCW60B	SAMS	npn	V _{CB0} =32 B; I _C =100 мA; P _D =350 мВт; h ₂₁ =180310; f _T >125 МГц	SOT23,SOD23	B·E·C
AB	BCW60B	ZETEX	npn	$V_{C80}=32B$; $I_{C}=200$ mA; $P_{D}=330$ mBr; $h_{21}=180310$; $f_{T}>250$ MF $_{L}$	SOT23,SOD23	B-E-C
ABA	CMPD4150	CSI	dih	I_F =250 MA; V_R =50 B; V_F (I_F =100 MA)=0.820.92 B; I_R < 100 HA; t_{RR} <4.0 HC; C_T <4.0 π Q	SOT23,SOD23	A·n.c.·K
ABA	MAX803MXR	MAX	mrc	V _{тв} =4.38B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{CC}
ABA	TMPD4150	ALLEG	d	I_F < 600 mA; V_{BR} > 75B; V_F (I_F =1 mA) < 0.62B; I_R < 100 nA; t_{RR} < 4.0 nc; C_0 < 2.5 n Φ	SOT23,SOD23	A·n.c.·K
ABAA	MAX809MUR	MAX	mrc	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <100 мкА	SOT23,SOD23	GND · RST · V _{CC}
ABB	MAX803TXR	MAX	mrc	V _{тп} =3.08B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{CC}
ABC	MAX803SXR	MAX	mrc	V _{TR} =2.93B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{CC}
ABC	TMPD4154	ALLEG	d	I_F <600 mA; V_{BR} >35B; $V_{E}(I_F$ =30 mA)<1.0B; I_{R} <100 hA; t_{RR} <4.0 hc; C_0 <4.0 n Φ	SOT23,SOD23	A·n.c.·K
ABD	MAX803RXR	MAX	mrc	V _{TR} =2.63B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{CC}
ABE	MAX803ZXR	MAX	mrc	V _{TR} =2.32B; V _{DD} =1.25.5B; I _{CC} <60 мкА	SOT323,SC70	GND · RST · V _{CC}
ABF	LM4041ADX3-1.2	MAX	vref	V _{DUT} =1.225B; ACC=0.1 %	SOT323,SC70	+n.c.
ABG	LM4041BIX3-1.2	MAX	vref	V _{DUT} =1.225B; ACC=0.2 %	SOT323,SC70	+n.c.
ABH	LM4041CIX3-1.2	MAX	vref	V _{DUT} =1.225B; ACC=0.5%	SOT323,SC70	+n.c.
ABI	LM4041DIX3-1.2	MAX	vref	V _{DUT} =1.225B; ACC=1.0 %	SOT323,SC70	+n.c.
ABJ	LM4040AIX3-2.1	MAX	vref	V _{OUT} =2.048B; ACC=0.1%	SOT323,SC70	+n.c.
ABK	LM4040BIX3-2.1	MAX	vref	V _{OUT} =2.048B; ACC=0.2%	SOT323,SC70	+n.c.
ABL	LM4040CIX3-2.1	MAX	vref	V _{OUT} =2.048B; ACC=0.5%	SOT323,SC70	+n.c.





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
ABM	LM4040DIX3-2.1	MAX	vref	V _{OUT} =2.048 B; ACC=1.0%	S0T323,SC70	+n.c.
ABN	LM4040AIX3-2.5	MAX	vref	V _{DUT} =2.500 B; ACC=0.1%	S0T323,SC70	+•n.c.
ABO	LM4040BIX3-2.5	MAX	vref	V ₀₁₀₇ =2.500 B; ACC=0.2%	SOT323,SC70	+n.c.
ABo	BCW60B	PHIL	non	V _{CR0} =32B; I _C =200 MA; P _D =250 MBT; h ₂₁ =180320; f _T >100 MFu	SOT23,SOD23	B·E·C
ABP	LM4040CIX3-2.5	MAX	vref	V _{OUT} =2.500 B; ACC=0.5%	SOT323,SC70	+n.c.
ABQ	LM4040DIX3-2.5	MAX	vref	V _{DUT} =2.500 B; ACC=1.0%	S0T323,SC70	+n.c.
ABR	LM4040AIX3-3.0	MAX	vref	V _{DUT} =3.000 B; ACC=0.1%	S0T323,SC70	+n.c.
ABs	BCW60B	SIEM	non	V _{CB0} =32B; I _C =100мA; P _D =330мBт; h ₂₁ =180310; f ₇ =250МГц	SOT23,SOD23	B·E·C
ABS	LM4040BIX3-3.0	MAX	vref	V _{DUT} =3.000 B; ACC=0.2%	S0T323,SC70	+n.c.
ABt	BCW60B	PHIL	non	V _{GB0} =32B; I _G =200 MA; P _D =250 MBT; h _{D1} =180320; f _T >100 MFu	SOT23.SOD23	B·E·C
ABT	LM4040CIX3-3.0	MAX	vref	V _{OUT} =3.000 B; ACC=0.5%	SOT323,SC70	+n.c.
ABU	LM4040DIX3-3.0	MAX	vref	V _{DUT} =3.000 B; ACC=1.0%	S0T323.SC70	+n.c.
ABV	LM4040AIX3-4.1	MAX	vref	V _{DUT} =4.096 B; ACC=0.1%	S0T323,SC70	+n.c.
ABW	LM4040BIX3-4.1	MAX	vref	V _{DUT} =4.096 B; ACC=0.2%	S0T323.SC70	11 22/10030
ABX	LM4040CIX3-4.1	MAX	vref	V _{DIT} =4.096 B; ACC=0.5%	S0T323,SC70	
ABY	LM4040DIX3-4.1	MAX	vref	V _{DIJT} =4.096 B; ACC=1.0%	S0T323,SC70	
ABZ	LM4040AIX3-5.0	MAX	vref	V _{DUI} =5.000 B; ACC=0.1%	S0T323,SC70	
AC	2SD1101	REN	non	V _{CB0} =25B; I _C =700 MA; P _D =150 MBT; h ₂₁ =120240	SOT23.SOD23	
AC	BCW60C	ALLEG	non	V _{CB0} =32B; I _{CB0} <20HA; h ₂₁ =250460; V _{CB1sati} <0.35B; f _T >125MF _I ₄	SOT23.SOD23	
AC	BCW60C	CDIL	non	V _{CB0} *32B; I _C *200мA; P _D *330мBт; h ₂₁ *250460; f _T >250МГц	SOT23.SOD23	70070070
AC	BCW60C	SAMS	npn	V _{CB0} =32B; I _C =100мA; P _D =350мBт; h ₂₁ =250460; f _T >125МГц	SOT23,SOD23	152.50 00
AC	BCW60C	ZETEX	non	V _{CB0} -32B; I _C =200мA; P _D =330мBт; h ₂₁ =250460; f _T >250МГц	SOT23, SOD23	
ACA	LM4040BIX3-5.0	MAX	vref	V _{DITI} =5.000 B; ACC=0.2%	SOT323,SC70	
ACAA	MAX809TUR	MAX	mrc	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{DC} <100мкА		GND · RST · V _{CC}
ACB	LM4040CIX3-5.0	MAX	yref	V _{DITT} =5.000 B; ACC=0.5%	S0T323,SC70	
ACC	LM4040DIX3-5.0	MAX	yref	V _{DIT} =5.000 B; ACC=1.0%	S0T323,SC70	10 0000000
ACD	MAX6808XR32	MAX	vd	V _{IR} =3.2B; V _{DR} =1.25.5 B; l _{DE} <80 m/sA		RST-GND-V _{CC}
ACE	MAX6326XR31	MAX	mrc	V _{IB} =3.08 B; V _{DD} =1.25.5 B; I _{DC} <1.75 mKA	S0T323,SC70	
ACF	MAX6347XP46	MAX	mrc	V _{TB} =4.6B; V _{DD} =1.25.5B; l _{CC} <1.75MKA	S0T323,SC70	
ACH	MAX6326XR23	MAX	mrc	V _{TR} =2.32B; V _{nn} =1.25.5B; I _{cc} <1.75mkA	SOT323,SC70	
ACI	MAX6326XR26	MAX				GND-RST-V _{CC}
ACJ	MAX6328XR26	MAX	mrc mrc	V _{IR} =2.63B; V _{DD} =1.25.5B; I _{CC} <1.75 m/A		
	MAX6346XP44	MAX		V _{TR} =2.63B; V _{DD} =1.25.5B; I _{CC} <1.75 m/A		GND · RST · V _{CC} GND · RST · V _{CC}
ACK ACL		ROHM	mrc	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <1.75 m/A		
	2SC3837KL		npn	V _{CBO} *30 B; I _C *50 κA; P _D * 150 κBτ; h ₂₁ *2756; f _T * 1500 ΜΓц	SOT346,SC59	
ACL	MAX6347XR44	MAX	mrc	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA	S0T323,SC70	
ACM	2SC3837KM	ROHM	npn	V _{CB0} *30B; I _G *50mA; P _D *150mBt; h ₂₁ *3982; f _T *1500 MFu	SOT346,SC59	NO. 15 TO 15
ACM	MAX6348XR44	MAX	mrc	V _{TR} =4.38B; V ₀₀ =1.25.5B; I _{CC} <1.75 mkA		GND · RST · V _{CC}
ACN	2SC3837KN	ROHM	npn	V _{CB0} =30B; I _C =50mA; P _D =150mBτ; h ₂₁ =56120; f _T =1500MΓц	SOT346,SC59	20000000
ACN	2SC4725N	ROHM	npn	V _{CB0} =30 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =56120; f _T =1500 МГц	SOT416,SC75A	
ACN	2SC5661N	ROHM	npn	V _{CB0} =30B; I _C =50мA; P _D =150мВт; h ₂₁ =56120; f _T =1500МГц	VMT3,VMD3	B·E·C
ACN	MAX6348XR46	MAX	mrc	V _{TR} =4.6B; V _{DD} =1.25.5B; I _{DD} <1.75mkA		GND - RST - V _{CC}
ACO	MAX6346XP46	MAX	mrc	V _{TR} =4.63B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA		GND · RST · V _{CC}
ACP	2SC3837KP	ROHM	npn	V _{C80} =30 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =82180; f _T =1500 МГц	SOT346,SC59	
ACP	2SC4725P	ROHM	non	V _{CB0} =30B; I _C =50мA; P _D =150мВт; h ₂₁ =82180; f _T =1500МГц	SOT416,SC75A	
ACP	2SC5661P	ROHM	npn	V _{CB0} =30B; I _C =50мA; P _D =150мВт; h ₂₁ =82180; f _T =1500МГц	VMT3,VMD3	B·E·C
ACp	BCW60C	PHIL	npn	V _{CB0} =32 B; I _C =200 mA; P ₀ =250 mBτ; h ₂₁ =250460; f ₁ >100 MΓц	SOT23,SOD23	11. 50. 10
ACP	MAX6326XR29	MAX	mrc	V _{TR} =2.93 B; V _{DD} =1.25.5 B; I _{CC} < 1.75 мкA	S0T323,SC70	
ACQ	2SC3837KQ	ROHM	npn	V _{CB0} =30 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =120270; f _T =1500 МГц	SOT346,SC59	
ACQ	MAX6327XR23	MAX	mrc	V _{TR} =2.32B; V _{DD} =1.25.5B; I _{CC} < 1.75 мкA	SOT323,SC70	
ACQ	MAX6377XR24	MAX	٧d	V _{TR} =2.40B; V _{DD} =1.25.5B; I _{CC} < 1.75 мкA		GND+OUT+V _{CC}
ACR	MAX6327XP26	MAX	mrc	V _{TR} =2.63 B; V _{DD} =1.25.5 B; I _{CC} < 1.75 мкA	S0T323,SC70	
ACs	BCW60C	SIEM	non	V _{CB0} =32 B; I _C =100 mA; P _D =330 mBT; h ₂₁ =250460; f _T =250 MFu,	SOT23,SOD23	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
ACS	MAX6327XR29	MAX	mrc	V _{TR} =2.93B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA	SOT323,SC70	GND · RST · V _{CC}
ACt	BCW60C	PHIL	npn	V _{CB0} =32 B; I _C =200 мA; P _D =250 мВт; h ₂₁ =250460; f _T >100 МГц	SOT23,SOD23	B·E·C
ACT	MAX6327XR31	MAX	mrc	V _{TB} =3.08B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	S0T323,SC70	GND · RST · V _{CC}
ACU	MAX6328XR23	MAX	mrc	V _{TB} =2.32B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА		GND · RST · V _{CC}
ACV	MAX6328XR29	MAX	mrc	V _{TB} =2.93B; V _{DD} =1.25.5B; I _{CC} <1.75 MKA		GND · RST · V _{CC}
ACW	MAX6328XR31	MAX	mrc	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA	SOT323,SC70	GND · RST · V _{CC}
ACZ	MAX6375XR26	MAX	vd	V _{TR} =2.63B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA	SOT323.SC70	GND · OUT · V
AD	BCW60D	ALLEG	non	V _{CB0} =32B; I _{CB0} <20 HA; h ₂₁ =380630; V _{CE(sat)} <0.35B; f ₇ >125 MFu,	SOT23,SOD23	
AD	BCW60D	CDIL	non	V _{G80} =32B; I _C =100 мA; P _D =350 мBт; h ₂₁ =380630; f _T >125 МГц	SOT23,SOD23	
AD	BCW60D	SAMS	npn	V _{C80} =32 B; I _C =100 MA; P _D =350 MBr; h ₂₁ =380630; f _T >125 MFu	SOT23,SOD23	
AD	BCW60D	ZETEX	non	V _{C80} =32 B; I _C =200 MA; P _D =330 MBT; h ₂₁ =380630; f _T >250 MFu	SOT23,SOD23	
ADA	MAX6376XR29	MAX	vd	V _{TB} =2.93B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА		GND · OUT · V _{CI}
ADAA	MAX809SUR	MAX	mrc	V _{тВ} =2.93B; V _{DD} =1.25.5B; I _{CC} <100 мкА		GND · RST · V _{CC}
ADB	MAX6377XR23	MAX	vd	V _{TB} =2.32B; V _{DD} =1.25.5B; I _{CC} <1.75 mKA	SOT323,SC70	GND · OUT · V _{CI}
ADC	MAX6377XR29	MAX	٧d	V _{TB} -2.93B; V _{DD} -1.25.5B; I _{CC} <1.75 mKA		GND · OUT · V _{CI}
ADD	MAX6378XR46	MAX	٧d	V _{TR} -2.55B, V _{DD} -1.25.5B, I _{CC} <1.75 MKA	SOT323,SC70	GND · OUT · Vo
ADE	MAX6379XR44	MAX	aq	V _{TB} : 4.38B; V _{DD} : 1.25.5B; I _{DD} : 1.75 MKA	S0T323,SC70	GND · OUT · V _{CI}
ADF		MAX				
1,100	MAX6380XR46	100000	Aq	V _{IR} =4.63B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA		GND OUT VO
ADH	MAX6375XR22	MAX	٧d	V _{TR} =2.20B; V _{DD} =1.25.5B; I _{CC} <1.75 mKA	SOT323,SC70	GND OUT VCC
ADI	MAX6375XR23	MAX	vd	V _{TR} =2.32B; V _{DD} =1.25.5B; I _{CC} <1.75 mKA	SOT323,SC70	GND · OUT · V _{CC}
ADJ	MAX6375XR29	MAX	Aq	V _{TR} =2.93B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT323,SC70	GND · OUT · V _{CC}
ADK	MAX6375XR31	MAX	Aq	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT323,SC70	GND · OUT · V _{CI}
ADL	2SC3838KL	ROHM	npn	V _{CB0} =20B; I _C =50мA; P _D =150мBт; h ₂₁ =2756; f _T =3200МГц	SOT346,SC59	
ADL	MAX6376XR22	MAX	٧d	V _{TR} =2.20B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA	SOT323,SC70	GND · OUT · V _{CC}
ADM	2SC3838KM	ROHM	npn	V _{CB0} =20 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =3982; f _T =3200 МГц	SOT346,SC59	B-E-C
ADM	MAX6376XR23	MAX	Aq	V _{TR} =2.32B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT323,SC70	GND · OUT · V _{CC}
ADN	2SC3838KN	ROHM	npn	V _{CB0} =20 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =56120; f _T =3200 МГц		B-E-C
ADN	2SC4726N	ROHM	npn	V _{CB0} =20 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =56120; f _T =3200 МГц	SOT416,SC75A	
ADN	2SC5662N	ROHM	npn	V ₀₈₀ =20 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =56120; f _T =3200 МГц	VMT3,VMD3	B-E-C
ADN	MAX6376XR26	MAX	Aq	V _{TR} =2.63B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА		GND · OUT · V _{CI}
ADO	MAX6376XR31	MAX	νd	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT323,SC70	GND · OUT · V _{CC}
ADP	2SC3838KP	ROHM	npn	V _{C80} =20 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =82180; f _T =3200 МГц	SOT346,SC59	B-E-C
ADP	2SC4726P	ROHM	npn	V _{CB0} =20B; I _C =50 мA; P _D =150 мВт; h ₂₁ =82180; f _T =3200 МГц	SOT416,SC75A	B-E-C
ADP	2SC5662P	ROHM	npn	V _{CB0} =20B; I _C =50 мA; P _D =150 мВт; h ₂₁ =82180; f _T =3200 МГц	VMT3,VMD3	B-E-C
ADp	BCW60D	PHIL	npn	V _{CB0} =32 B; I _C =200 мA; P _D =250 мВт; h ₂₁ =380630; f _T >100 МГц	SOT23,SOD23	B·E·C
ADP	MAX6377XR22	MAX	мq	V _{TR} =2.20B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT323,SC70	GND · OUT · V _{CC}
ADQ	2SC3838KQ	ROHM	npn	V _{CB0} =20 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =120270; f _T =3200 МГц	SOT346,SC59	B·E·C
ADQ	MAX6377XR26	MAX	vd	V _{TR} =2.63B; V _{DD} =1.25.5B; I _{DC} <1.75 мкА	SOT323,SC70	GND · OUT · V _{CC}
ADR	MAX6377XR31	MAX	vd	V _{TB} =3.08B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA		GND · OUT · V _{CC}
ADs	BCW60D	SIEM	ngn	V _{CB0} =32 B; I _C =100 MA; P _D =330 MBT; h _{D1} =380630; f _T =250 MFu	SOT23,SOD23	
ADS	MAX6378XR44	MAX	νd	V _{TB} =4.38B; V _{DD} =1.25.5B; I _{CC} <1.75 mKA		GND · OUT · V _{CC}
ADt	BCW60D	PHIL	npn	V _{CBB} =32 B; I _C =200 мA; P _D =250 мBт; h ₂₁ =380630; f _T >100 МГц	SOT23,SOD23	
ADT	MAX6379XR46	MAX	Aq	V _{TB} =4.63B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT323.SC70	GND · OUT · V _{GC}
ADU	MAX6380XR44	MAX	٧d	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <1.75 mKA		GND · OUT · Vot
ADW	MAX6380XR42	MAX	vd	V _{TB} =4.20B; V _{DD} =1.25.5B; I _{CC} <1.75 mKA		GND · OUT · V _{CI}
ADX	MAX6375XR28	MAX	vd	V _{TB} =2.80B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA		GND · OUT · V _{CI}
ADY			mrc	V _{TB} =1.58B; V _{DD} =1.25.5B; I _{SC} <1.75 MKA	S0T323,SC70	GND · RST · V _{CC}
ADZ		_	mrc	V _{TB} -2.63B; V _{DD} -15.5B; I _{CC} <13 MKA	SOT323,SC70	GND · RST · V _{GC}
AEA		_	_			GND · RST · V _{CC}
AEB		-	mrc	V _{TR} =1.67B; V _{DD} =155B; I _{CC} <13 m/A		
		2000	mrc	V _{TR} =4.63B; V _{DD} =15.5B; I _{CC} <13 мкA	SOT323,SC70	GND · RST · V _{CC}
AEL	2SC3839KL	ROHM	npn	V _{GB0} =30 B; I _G =50 MA; P _D =150 MBT; h ₂₁ =2756; f _T >200 MFu		B-E-C
AEM	2SC3839KM	ROHM	npn	V_{CB0} =30 B; I_C =50 mA; P_D =150 mBT; h_{21} =3982; f_T >200 MFu	SOT346,SC59	B-E-C





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
AEN	2SC3839KN	ROHM	npn	V _{CB0} =30 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =56120; f _T >200 МГц	SOT346,SC59	B·E·C
AEP	2SC3839KP	ROHM	npn	V _{CB0} =30 B; I _C =50 мА; P _D =150 мВт; h ₂₁ =82180; f _T >200 МГц	SOT346,SC59	B·E·C
AEQ	2SC3839KQ	ROHM	npn	V _{CB0} =30 B; I _C =50 мА; P ₀ =150 мВт; h ₂₁ =120270; f _T >200 МГц	SOT346,SC59	B·E·C
AFAA	MAX809RUR	MAX	mrc	V _{TR} =2.63B; V _{DD} =1.25.5B; I _{CC} <100 мкА	SOT23,SOD23	GND · RST · V _{CC}
AFP	2SD1781KP	ROHM	npn	V _{CB0} =40 B; I _C =800 мА; P _D =200 мВт; h ₂₁ =82180; f _T >150 МГц	SOT346,SC59	B·E·C
AFQ	2SD1781KQ	ROHM	non	V _{CR0} =40 B; I _C =800 мА; P _D =200 мВт; h ₂₁ =120270; f _T >150 МГц	SOT346,SC59	B·E·C
AFR	2SD1781KR	ROHM	non	V _{CR0} =40 B; I _C =800 MA; P _D =200 MBT; h ₂₁ =180390; f _T >150 MFu	SOT346,SC59	B·E·C
AFs	BCW60FF	SIEM	non	V _{CR0} =32 B; I _C =100 mA; P _D =330 mBT; h ₂₁ =250460; f _T =250 MFu	SOT23, SOD23	B·E·C
AG	BCX70G	ALLEG	non	V _{CB0} =45B; I _{CB0} <20 HA; h ₂₁ =120220; V _{CEIsati} <0.35B; f _T >125 MFu,	SOT23.SOD23	B·E·C
AG	BCX70G	CDIL	non	V _{CBD} =45B; I _G =200 мA; P _D =250 мВт; h ₂₁ =120220; f _T >100 МГц	SOT23,SOD23	
AG	BCX70G	SAMS	non	V _{CB0} =45B; I _C =200 мA; P _D =350 мВт; h ₂₁ =120220; f _T >125МГц	SOT23.SOD23	
AG	BCX70G	ZETEX	non	V _{CB0} =45B; I _C =200мA; P _D =330мВт; h ₂₁ =120220; f _T >250МГц	SOT23,SOD23	
AG	BRA144ECM	REN	Dono	V _{CC} =50 B; I _{CUT} =100 мА; P _D =150 мВт; h ₂₁ >70; 47 к/47 к	S0T323,SC70	
AG	BRA144EMP	REN	Dono	V _{CC} =50 B; I _{CHT} =100 MA; P _D =150 MB; h ₂₁ >70; 47 к/47 к	SOT23.SOD23	
	MAX810LUR	MAX	mrc	V _{тВ} =4.63B; V _{пП} =1.25.5B; I _{пС} <100мкА	-	GND-RST-V _{cc}
AGo	BCX70G	PHIL	non	V _{CR0} =45B; I _C =200 MA; P _D =250 MBτ; h ₂₁ =120220; f _T >100 MΓц	SOT23,SOD23	- 00
AGs	BCX70G	SIEM	non	V _{CBD} =45B, I _C =200 MA, P _D =230 MBT, I ₁₂₁ =120220, I _T > 100 MTц	SOT23,SOD23	
AGt	BCX70G	PHIL	non	V _{CR0} =45B; I _C =200 mA; P _D =250 mB1; I _D =120220; I _T =250 mII _L V _{CR0} =45B; I _C =200 mA; P _D =250 mB1; I _D =120220; I _T >100 MII _L	SOT23,SOD23	
AH	1SS345	SANYO	shd	000 10 10 10	SOT23,SOD23	
AH	1770000000000			V _R >55B; V _R (I _E =1 мA) <0.35B; I _R (V _R =40 B) <50 мкA; C _T <120 πΦ		NE 0 0 0 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1
	BCX70H	ALLEG	npn	V _{CB0} =45B; I _{CB0} <20 нА; h ₂₁ =180310; V _{CE(sat)} <0.35B; f _T >125МГц	SOT23,SOD23	100000
AH	BCX70H	CDIL	npn	V _{CB0} =45 B; I _C =200 мА; P _D =250 мВт; h ₂₁ =250460; f _T >100 МГц	SOT23,SOD23	
AH	BCX70H	SAMS	npn	V _{CB0} =45B; I _C =200мA; P _D =350мBт; h ₂₁ =180310; f _T >125МГц	SOT23,SOD23	
AH	BCX70H	ZETEX	npn	V _{CB0} =45B; I _C =200мA; P _D =330мBт; h ₂₁ =180310; f _T >250МГц	SOT23,SOD23	
AHAA	MAX810MUR	MAX	mrc	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <100 mKA		GND · RST · V _{CC}
AHP	2SB1197KP	ROHM	pnp	V _{CB0} =40 B; I _C =800 мA; P _D =200 мВт; h ₂₁ =82180; f _T >200 МГц	SOT346,SC59	122233333
AHp	BCX70H	PHIL	npn	V _{CB0} =45B; I _C =200 мА; P _D =250 мВт; h ₂₁ =250460; f _T >100 МГц	SOT23,SOD23	T0071170
AHQ	2SB1197KQ	ROHM	pnp	V _{CB0} =40 B; I _C =800 мА; P _D =200 мВт; h ₂₁ =120270; f _T >200 МГц	SOT346,SC59	
AHR	2SB1197KR	ROHM	pnp	V _{CB0} =40 B; I _C =800 мA; P _D =200 мВт; h ₂₁ =180390; f _T >200 МГц	SOT346,SC59	
AHs	BCX70H	SIEM	npn	V _{CB0} =45B; I _C =100мA; P _D =330мBт; h ₂₁ =180310; f _T =250МГц	SOT23,SOD23	
AHt	BCX70H	PHIL	npn	V _{CB0} =45 B; I _C =200 мА; P _D =250 мВт; h ₂₁ =250460; f _T >100 МГц	SOT23,SOD23	325-77-0500
AJ	BCX70J	ALLEG	npn	V_{CB0} =45B; I_{CB0} <20 HÅ; h_{21} =250460; $V_{CE[sat]}$ <0.35B; f_T >125M Γ_{II}	SOT23,SOD23	B·E·C
AJ	BCX70J	CDIL	npn	V_{CB0} =45 B; I_C = 100 mA; P_D =330 mBT; h_{21} =250460; f_T >250 M Γ_{LL}	SOT23,SOD23	B·E·C
AJ	BCX70J	SAMS	non	V _{CB0} =45 B; I _C =200 мА; P _D =350 мВт; h ₂₁ =250460; f _T >125 МГц	SOT23,SOD23	B-E-C
AJ	BCX70J	ZETEX	npn	V _{CB0} =45 B; I _C =200 MA; P _D =330 MBT; h ₂₁ =250460; f _T >250 MFU	SOT23,SOD23	B·E·C
AJAA	MAX810TUR	MAX	mrc	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{CC} <100мкА	SOT23,SOD23	GND · RST · V _{CC}
AJP	2SD1782KP	ROHM	npn	V _{CB0} =80 B; I _C =500 мА; P ₀ =200 мВт; h ₂₁ =82180; f _T >180 МГц	SOT346,SC59	B·E·C
AJp	BCX70J	PHIL	npn	V _{CB0} =45 B; I _C =200 мA; P _D =250 мВт; h ₂₁ =180310; f _T >100 МГц	SOT23,SOD23	B·E·C
AJQ	2SD1782KQ	ROHM	non	V _{CR0} =80 B; I _C =500 мА; P _D =200 мВт; h ₂₁ =120270; f _T > 180 МГц	SOT346,SC59	B·E·C
AJR	2SD1782KR	ROHM	non	V _{CB0} =80 B; I _C =500 мА; P ₀ =200 мВт; h ₂₁ =180390; f ₁ >180 МГц	SOT346,SC59	B·E·C
AJs	BCX70J	SIEM	non	V _{CR0} =45B; I _C =100mA; P _D =330mBT; h ₂₁ =250460; f _T =250MFµ	SOT23.SOD23	B-E-C
AJt	BCX70J	PHIL	non	V _{CR0} =45B; I _G =200 MA; P _D =250 MBT; h ₂₁ =180310; f _T >100 MFц	SOT23,SOD23	
AK	BCX70K	ALLEG	non	V _{CB0} =45B; I _{CB0} < 20 HA; h ₂₁ =380630; V _{CFIset} < 0.35B; f _T >125MFu	SOT23,SOD23	
AK	BCX70K	CDIL	non	V _{CBD} :45B; I _C :200 мA; P _D : 250 мВт; I _{D2} :380630; f _T > 100 МГц	SOT23,SOD23	
AK	BCX70K	SAMS	non	V _{CB0} =45B; I _C =200 MA; P _D =350 MBT; I _{D2} =380630; f _T >125 MFu	SOT23,SOD23	
AK	BCX70K	ZETEX	non	V _{CR0} =45B; I _C =200 MA; P _D =330 MBT; I _{D2} =380630; f _T >250 MFц	SOT23.SOD23	
AKAA	MAX810SUR	MAX	mrc	V _{IB} =2.93B; V _{DD} =1.25.5B; I _{DC} <100мкА		GND · RST · V _{CC}
AKP	2SB1198KP	ROHM	pnp	V _{CBO} =80 B; I _C =500 мA; P _D =200 мBт; h ₂₁ =82180; f _T >180 МГц	S0T346,SC59	
AKo	BCX70K	PHIL	non	V _{CB0} =45 B; I _C =200 MA; P _D =250 MBτ; I _{D2} =380630; f _T >100 MΓ _U	SOT23,SOD23	
AKQ	2SB1198KQ	ROHM	pnp	V _{CBO} =80 B; I _C =500 mA; P _D =200 mBτ; I ₁₂ =350350; I ₇ >100 mTц	SOT346,SC59	
AKR.	2SB1198KR	ROHM	prip	V _{CBO} =80 B; I _C =500 мA; P _D =200 мBт; I _{D2} =120270; I _T > 180 МГц	S0T346,SC59	
AKS	BCX70K	SIEM			SOT23,SOD23	100000000000000000000000000000000000000
	MAX810RUR	MAX	npn	V _{CB0} =45 B; I _C =100 mA; P _D =330 mB; h ₂₁ =380630; f _T =250 MFu		
ALAA	MUNUT QYYMA	MAX	mrc	V _{TR} =2.63 B; V _{DD} =1.25.5 B; I _{DC} < 100 мкA	00123,50023	GND · RST · V _{CC}

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
ALM	2SC3802KM	ROHM	npn	V _{C80} =30B; I _C =30mA; P _D =200 mBr; h ₂₁ =3982; f _T >110 MFu	SOT346,SC59	B-E-C
ALN	2SC3802KN	ROHM	npn	V _{CB0} +30B; I _C +30мA; P _D +200мBт; h ₂₁ +56120; f _T >110МГц	SOT346,SC59	B·E·C
ALP.	2SC3802KP	ROHM	npn	V ₀₈₀ =30B; I _C =30мA; P _D =200мВт; h ₂₁ =82180; f _T >110МГц	SOT346,SC59	
ALQ	2SC3802KQ	ROHM	non	V _{csn} =30B; I _c =30мA; P _n =200мВт; h ₂₁ =120270; f _T >110МГц	SOT346,SC59	
AM	BSS64	MOT	npn	V _{CBO} =120 B; I _C =800 мA; P _D =330 мВт; h _{P1} =2080; f _T =100 МГц	SOT23,SOD23	1000000000
AM	MMBT3904WT1	MOT	npn	V _{DB0} =60 B; I _C =200 мA; P _D =300 мВт; h ₂₁ =100300; f _T >200 МГц	SOT323,SC70	100000000000000000000000000000000000000
AMN	2SC4018KN	ROHM	npn	V _{сво} =40 B; I _C =100 мA; P _D =200 мВт; h ₂₁ =56120; f _T >230 МГц	SOT346,SC59	B·E·C
AMP	2SC4018KP	ROHM	ngn	V _{CRO} =40 B; I _C =100 мA; P _D =200 мВт; h ₂₁ =82180; f _T > 230 МГц	SOT346,SC59	
AMp	BSS64	PHIL	non	V _{CB0} =120 B; I _C =100 mA; P _D =250 mB _T ; h _{P1} >20; f _T >60	SOT23,SOD23	
AMs	BSS64	SIEM	npn	V _{G80} =120 B; I _C =800 мА; P _D =330 мВт; h ₂₁ =2080; f _T =100 МГц	SOT23,SOD23	
AMt	BSS64	PHIL	npn	V _{CR0} =120 B; I _C =100 mA; P _D =250 mBT; h _{P1} >20; f _T >60	SOT23,SOD23	
AN	2SC2413KN	ROHM	non	V _{G80} =40B; I _C =50мA; P _D =200 мВт; h ₂₁ =56120; f _T =300 МГц	SOT346.SC59	177000000000
AN	2SC2532	TOSH	npn	V _{CE0} =40 B; I _C =300 mA; P _D =150 mBT; h ₂₁ >5000	SOT346,SC59	1000000000
AN	2SC4098N	ROHM	non	V ₀₈₀ =40 B; I _C =50 мA; P _D =200 мВт; h ₂₁ =56120; f _T =300 МГц	SOT323.SC70	1855/A DA
AN	2SC4618N	ROHM	ngn	V _{CR0} =40 B; I _C =50 mA; P _D =150 mBr; h ₂₁ =56120; f _T >300 MFu	SOT416,SC75A	100-110-100
AN	2SC5659N	ROHM	npn	V _{CEO} =25B; I _C =50 MA; P _D =300 MBr; h ₂₁ =56120; f _T >150 MFц	VMT3,VMD3	B·E·C
AN	2SK3287	REN	nMOS	V _{DS} =30 B; I _D =300 MA; P _D =400 MBT; R _{DSInnl} <3.440M	SOT23,SOD23	
AN	2SK3289	REN	nMOS	V _{DS} =30 B; I _D =300 MA; P _D =400 MB1; R _{DS(DI)} >3.440 M	SOT323,SC70	100000000000000000000000000000000000000
ANM	2SC4061KM	ROHM	non	V _{DS} =300 B; I _C =300 MA; P _D =400 MB1; H _{DS} (_{DI}) > 3.44 0 M V _{CR0} =300 B; I _C =100 MA; P _D =200 MB1; h _{Pl} =3982; f _T >100 MFu	SOT346,SC59	
ANN	2SC4061KN	ROHM	non	V _{C80} =300 B; I _C =100 MA; P _D =200 MB1; I _{E1} =39o2; I _T >100 MII ц V _{C80} =300 B; I _C =100 MA; P _D =200 MB1; I _{E1} =56120; I _T >100 MII ц	SOT346,SC59	3102 12 130
ANP	2SC4061KN	ROHM	1		SOT346,SC59	32230 22
ANS			npn	V _{C80} =300 B; I _C =100 mA; P _D =200 mBr; h ₂₁ =82180; f _T >100 MFц	-	
	BCW60FN	SIEM	npn	V _{CB0} =32B; I _C =100 mA; P _D =330 mBr; h ₂₁ =380630; f _T =250 MFu	SOT23,SOD23	
AO AD	BCW60AR	III	npn	V _{C80} =32 B; I _C =200 мA; P _D =330 мBт; h ₂₁ =120220; f _T >250 MFц	SOT23,SOD23	
AP	2SC2413KP	ROHM	npn	V _{CB0} =40 B; I _C =50 mA; P _D =200 mBT; h ₂₁ =82180; f _T =300 MFц	SOT346,SC59	
AP	2SC4098P	ROHM	npn	V _{CB0} =40 B; I _C =50 mA; P _D =200 mBr; h ₂₁ =82180; f _T =300 MFц	SOT323,SC70	100000000000000000000000000000000000000
AP	2SC4618P	ROHM	npn	V _{GB0} =40 B; I _C =50 mA; P _D =150 mBT; h ₂₁ =82180; f _T >300 MFц	SOT416,SC75A	705.0
AP	2SC5659P	ROHM	npn	V _{CE0} =25B; I _C =50мA; P _D =300мBт; h ₂₁ =82180; f _T >150МГц	VMT3,VMD3	B·E·C
AP	2SJ575	REN	pMOS	V _{DS} =30 B; I _D =100 мА; P _D =400 мВт; R _{DS(on)} <7.9 Ом	SOT23,SOD23	
AP	2SJ576	REN	pMOS	V _{DS} =30 B; I _D =100 мА; P _D =400 мВт; R _{DS(on)} <7.9 Ом	SOT323,SC70	
AP	BCW60BR	Ш	npn	V _{CB0} =32 B; I _C =200 мА; P _D =330 мВт; h ₂₁ =180310; f _T >250 МГц	SOT23,SOD23	5.05.05
AP_	2SC4074K	ROHM	npn	V_{CB0} = 18 B; I_C = 50 mA; P_D = 150 mBT; h_{21} = 270; f_T > 1500 M Γ_{II}	SOT346,SC59	1000000
AQ	2SC2413KQ	ROHM	npn	V _{CB0} =40 B; I _C =50 мA; P _D =200 мВт; h ₂₁ =120270; f _T =300 МГц	SOT346,SC59	1.500.74 22
AQ	2SC4098Q	ROHM	npn	V _{GB0} =40 B; I _C =50 мA; Р ₀ =200 мВт; h ₂₁ =120270; f _T =300 МГц	SOT323,SC70	
AQ	2SC4618Q	ROHM	npn	V_{CB0} =40 B; I_C =50 mA; P_D =150 mBT; h_{21} =120270; f_T >300 MF $_{II}$	SOT416,SC75A	
AQ	2SC5659Q	ROHM	npn	V _{CE0} =25B; I _C =50мA; P _D =300 мВт; h ₂₁ =120270; f _T >150 МГц	VMT3,VMD3	B-E-C
A-Q	2PD1820AQ	PHIL	npn	V _{C80} °60 B; I _C °500 мA; P _D °200 мВт; h ₂₁ °85170; f _T > 150 МГц	SOT323,SC70	
A-Q	2PD1820AR	PHIL	npn	V _{CB0} =60 B; I _C =500 мА; P _D =200 мВт; h ₂₁ =120240; f _T >150 МГц	SOT323,SC70	100/03/11/03
AQP	2SB1051KP	ROHM	pnp	V_{C80} =40 B; I_C = 1000 мA; P_D =200 мBт; h_{21} =82180; f_T > 150 МГц	SOT346,SC59	1200000000
AQQ	2SB1051KQ	ROHM	pnp	V _{CB0} =40 B; I _C =1000 мА; Р _D =200 мВт; h ₂₁ =120270; f ₁ >150 МГц	SOT346,SC59	
AQR	2SB1051KR	ROHM	pnp	V_{C80} =40 B; I_C =1000 mA; P_D =200 mBt; h_{21} =180390; f_T >150 MFц	SOT346,SC59	B-E-C
AR	BCW60CR	ZETEX	npn	V _{CB0} =32 B; I _C =200 мA; P _D =330 мВт; h ₂₁ =250460; f _T >250 МГц	SOT23,SOD23	B·E·C
AR	BCW60CR	Ш	npn	V_{C80} =32B; I_C =200 мA; P_D =330 мBт; h_{21} =250460; f_T >250 МГц	SOT23,SOD23	C·B·E
AR	MSD709R	MOT	pnp	V _{C80} -25B	SOT23,SOD23	B-E-C
AS	2SA1655	SANYO	pnp	V _{CB0} =40 B; I _C =100 мA; P _D =200 мВт; h ₂₁ >30; f _T =200 МГц	SOT23,SOD23	B-E-C
AS	BAT1805	SIEM	cpin×2	V _R <35B; I _F <100 mA; V _F (I _F =100 mA)<1.2B; I _R <0.02 mkA; C _D <1.0 πΦ	SOT23,SOD23	A1+A2+K1,K2
AS	BCW60DR	Ш	npn	V _{C80} =32 B; I _C =200 мA; P _D =330 мВт; h ₂₁ =380630; f _T >250 МГц	SOT23,SOD23	C·B·E
AS	MSD709S	MOT	pnp	V ₀₈₀ -25B	SOT23,SOD23	B-E-C
A-S	2PD1820AS	PHIL	npn	V _{G80} =60 B; I _C =500 мА; P _D =200 мВт; h ₂₁ =170340; f _T >150 МГц	SOT323,SC70	B·E·C
ASA	BC846UA	AUK	npn	V _{сво} =80 B; I _C =100 мA; P _D =200 мВт; h ₂₁ =110220; f _T =150 МГц	SOT323,SC70	B·E·C
ASB	BC846UB	AUK	npn	V _{G80} =80 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =200450; f _T =150 МГц	SOT323,SC70	
ASC	BC846UC	AUK	npn	V _{C80} =80 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =420800; f _T =150 МГц	SOT323,SC70	
ASG	KTA1504	KEC	pnp	V _{CR0} =50 B; I _C =150 мA; P _D =150 мBr; h ₂₁ =200400; f _T >80 MFц	SOT23,SOD23	





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
ASO	KTA1504	KEC	pnp	V _{CB0} =50 B; I _C =150 мA; P _D =150 мВт; h ₂₁ =70140; f _T >80 МГц	SOT23,SOD23	B·E·C
ASs	BAT18-05	INF	cpin×2	V _R <35B; I _F <100 мA; V _E (I _F =100 мA)<1.2B; I _B <0.02 мкA; C _D <1.0 пФ	SOT23,SOD23	A1+A2+K1,K2
ASY	KTA1504	KEC	pnp	V _{CBD} =50B; I _C =150мA; P _D =150мBт; h ₂₁ =120240; f _T >80МГц	SOT23,SOD23	B·E·C
AT	BAT1806	SIEM	cpin×2	V _B <35B; I _E <100 мA; V _E (I _E =100 мA)<1.2B; I _B <0.02 мкА; С _D <1.0 пФ	SOT23,SOD23	K1-K2-A1,A2
AtQ	2PD1820AQ	PHIL	non	V _{сво} =60 B; I _с =500 мА; P _о =200 мВт; h ₂₁ =85170; f _T >150 МГц	SOT323,SC70	B·E·C
AtQ	2PD1820AR	PHIL	non	V _{CB0} =60 B; I _C =500 мА; P _D =200 мВт; h ₂₁ =120240; f _T >150 МГц	SOT323,SC70	B·E·C
ATQ	2SC4326KQ	ROHM	npn	V _{CB0} =12B; I _C =50 мA; P _D =150 мВт; h ₂₁ =120270; f _T >800 МГц	SOT346,SC59	B·E·C
ATR	2SC4326KR	ROHM	non	V _{CR0} =12B; I _C =50 MA; P _D =150 MBT; h ₂₁ =180390; f _T >800 MFu	SOT346,SC59	B·E·C
AtS	2PD1820AS	PHIL	non	V _{CBD} =60 B; I _C =500 мА; P _D =200 мВт; h ₂₁ =170340; f _T >150 МГц	SOT323,SC70	B·E·C
ATS	2SC4326KS	ROHM	non	V _{CB0} =12B; I _C =50 mA; P _D =150 mBT; h ₂₁ =270560; f _T >800 MFu	SOT346,SC59	
ATs	BAT18-06	SIEM		V _B <35B; I _E <100 мА; V _E (I _E =100 мА)<1.2B; I _B <0.02 мкА; C _D <1.0 пФ	SOT23.SOD23	
AU	BAT1804	SIEM	coin×2	The second secon	SOT23.SOD23	200 Car (100 Page 1
AUs	BAT18-04	INF		V _B <35B; I _F <100 мA; V _F (I _F =100 мA)<1.2B; I _B <0.02 мкА; С _D <1.0 пФ	SOT23.SOD23	
AV	DAN212K	ROHM	di	V _B <70B; I _F <200 mA; P _D <250 mB;; V _F (I _F =150 mA)<1.25B; t _{BB} <4 HC	SOT23.SOD23	
AW	BCX70GR	ZETEX	non	V _{CR0} =45B; I _C =200MA; P _D =330MBT; h ₂₁ =120220; f _T >250MFц	SOT23,SOD23	
AX	BCX70JR	ZETEX	non	V _{CR0} =45 B; I _C =200 MA; P _D =330 MBT; h ₂₁ =250460; f _T >250 MFц	SOT23,SOD23	
AX	BCX70JR	ITT	non	V _{CBO} =45 B; I _C =200 MA; P _D =330 MBr; h ₂₁ =250460; f _T >250 MFц	SOT23,SOD23	
AY	BCX70KR	ш	non	V _{CR0} =45 B; I _C =200 MA; P _D =330 MBT; h ₂₁ =380630; f _T >250 MFu	SOT23.SOD23	
AY	MMBD1000LT1	МОТ	di	V _B <30B; I _E <200 MA; V _E (I _E : 10 MA)<0.95 B; C _D <2nΦ; t _{BB} <3Hc	SOT23,SOD23	2020
AYAA	MAX6120EUR	MAX	vref	V _{IN} =2.411 B; I _{CC} <70 mKA; V _{DUT} =1.2B	SOT23,SOD23	
ATAA	MANDIZUEUN	MAA	ALG!	V _{IN} -2.411 Β, I _{CC} < 70 MKA, V _{OUT} -1.2 Β	30123,30023	GND
AZO	KTA1505	KEC	pnp	V _{CB0} =35B; I _C =500мA; P _D =150мBт; h ₂₁ =70140; f _T >200МГц	SOT23,SOD23	B·E·C
AZY	KTA1505	KEC	pnp	V _{CB0} =35B; I _C =500 мA; P _D =150 мВт; h ₂₁ =120240; f _T >200 МГц	SOT23,SOD23	B·E·C
В	IRLML2803	IR	nMOS	HEXFET; V _{DS} =30 B; I _D =0.9 A; P _D =540 MBT; P _{DS(on)} < 0.4 OM	SOT23,SOD23	G·S·D
В	MRF957T1	MOT	non	V _{CBD} =20B; I _C =100 мА; P _D =227 мВт; h ₂₁ =50200; f _T =9 ГГц	SOT323,SC70	B·E·C
В0	HSMS2810	HP	shd	V _{BB} > 20 B; V _E (I _E =35 mA) < 1.0 B; I _B (V _B =15 B) < 200 hA; C _D < 1.2 nΦ	SOT23,SOD23	A·n.c.·K
В0	HSMS281B	HP	shd	V _{BB} >20B; V _E (I _E =35 мA)<1.0B; I _B (V _B =15 B)<200 нA; C _D <1.2пФ	SOT323,SC70	A•n.c.•K
В0	SST5460	SIL	pFET	V _{DS} =40B; P _D =350 mBr; I _{DSS} =15 mA; g _E =1 mCm	SOT23,SOD23	D·S·G
B1	HSMS2811	HP	shd	V _{BB} >20B; V _E (I _E =35 мA)<1.0B; I _B (V _B =15B)<200 нA; C _D <1.2 пФ	SOT23.SOD23	n.c.+A+K
B1	SST5461	SIL	pFET	Vns=40B; Pn=350 мBт; Inss=>4 мA; gc>1 мСм	SOT23.SOD23	D·S·G
B10	KSC2715	SAMS	non	V _{GB0} =35B; I _G =50мA; P _D =150мВт; h ₂₁ =70140; f _T >150МГц	SOT23.SOD23	B·E·C
BIR	KSC2715	SAMS	non	V _{CBD} =35B; I _C =50мA; P _D =150мBт; h ₂₁ =4080; f _T >150МГц	SOT23,SOD23	B·E·C
B1Y	KSC2715	SAMS	non	V _{CR0} =35B; I _C =50 MA; P _D =150 MBT; h ₂₁ =120240; f _T >150 MFu	SOT23,SOD23	100000000000000000000000000000000000000
B2	BSV52	ZETEX	non	V _{CR0} =20B; I _C =100mA; P _D =330mBT; h ₂₁ =40120; f _T >500MF _U	SOT23.SOD23	10000000000
B2	BSV52LT1	MOT	non	V _{CRD} =20B; I _C =100 mA; P _D =300 mBT; h ₂₁ =40120; f _T >400 MFu	SOT23,SOD23	72.7
B2	HSMS2812	HP	shd×2	V _{BR} >20B; V _E (I _E =35 мА)<1.0B; I _R (V _B =15 B)<200 нА; C _D <1.2пФ	SOT23.SOD23	
B2	HSMS281C	HP	shd×2	V _{PR} >20B; V _E (I _E =35 MA)<1.0B; I _B (V _R =15B)<200 HA; C _D <1.2 πΦ	SOT323.SC70	
B2	SST5462	SIL	OFET	V _{DS} =40B; P _D =350 мВт; I _{DSS} =416 мА; g _E =2 мСм	SOT23.SOD23	
B26	BF570	PHIL	non	V _{CBO} =40 B; I _C =100 mA; P _D =250 mBr; h ₂₁ >40; f ₁ >490 MFu	SOT23.SOD23	5775 TO
B20	BSV52	PHIL	non	V _{CBO} =20B; I _C =100mA; P _D =250mBr; h ₂₁ =40120; f _T >400	SOT23.SOD23	0.0000000000000000000000000000000000000
B2t	BSV52	PHIL	non	V _{CR0} =20B; I _C =100 MA; P _D =250 MBr; h ₂₁ =40120; f _T >400	SOT23.SOD23	100000000000000000000000000000000000000
B3	1PS301	PHIL	fd×2	V _B <80B; I _F <250 mA; V _F (I _F =50 mA)<1.0 B; C _D <1.5 nΦ; I _{FB} <4 HC	SOT323.SC70	T
B3	1SS184	TOSH	di×2	V _R <80B; I _F <100 mA; V _E (I _F =100 mA)<1.2 B; I _R <0.5 mkA; t _{ER} <4 HC	SOT346,SC59	
B3	1SS301	TOSH	di×2	V _R <80B; I _F <100 MA; V _E (I _F : 100 MA)<1.2 B; I _B <4 Hc	SOT323.SC70	
B3	1SS361	TOSH	di×2	V _B <80B; I _C <100 MA; V _E (I _C =100 MA; <1.2 B; I _D <0.5 MKA; I _{DD} <4HC	SOT416,SC75A	
B3	1SS361F	TOSH	di×2	V _R <80B; I _F <100 MA; V _F (I _F : 100 MA)<1.2B; I _R <0.5 MKA; t _{RR} <4Hc	SOT490,SC89	San
B3	HSMS2813	HP	shd×2	V _{RR} > 20 B; V _R (I _F = 35 MA) < 1.0 B; I _R (V _R = 15 B) < 200 HA; C _D < 1.2 πΦ	SOT23.SOD23	
B3	HSMS281E	HP	shd×2		S0T323,S0D23	
B3	MMBD717LT1	MOT	shd×2	V _{BR} >20B; V _B (I _F =35 MA)<1.0B; I _B (V _B =15 B)<200 HA; C _D <1.2 πΦ	S0T323,SC70	10.00 Day 10.00
		GS	_	V _R >20B; V _F (I _F =1 мA) < 0.37B; C _T < 2.5 πΦ		
B31	IDB31		btd	V _{BO} = 3034 B; I _{TRM} = 2A; P _D = 150 mBτ	SOT23,SOD23	
B4	BSV52R	PHIL	npn	V _{CB0} =12B; I _C =200 MA; P _D =200 MBr; h ₂₁ =40; f _T >400	SOT23,SOD23	
B4	BSV52R	ZETEX	npn	V_{CB0} =20B; I_C =100mA; P_D =330mBr; h_{21} =40120; f_T >500M F_U	SOT23,SOD23	B.E.C

Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
B4	HSMS2814	HP	shd×2	V _{BB} >20 B; V _E (I _E =35 мA)<1.0 B; I _E (V _E =15 B)<200 нA; C _n <1.2 nΦ	SOT23,SOD23	A1-A2-K1,K2
B4	HSMS281F	HP	shd×2	$V_{BB} > 20 \text{ B}; V_{e}(I_{e}=35 \text{ mA}) < 1.0 \text{ B}; I_{B}(V_{B}=15 \text{ B}) < 200 \text{ HA}; C_{D} < 1.2 \text{ n}\Phi$	SOT323,SC70	A1 · A2 · K2 · K1
B5s	BBY58-05W	INF	var	V _B <10B; I _E <20 mA; I _B <0.01 mrA; C _{1 B} =17.519.3 mΦ; C _{4 B} =5.56.6 mΦ	SOT323.SC70	
B6	2SB815B6	SANYO	ono	V _{GB0} =20 B; I _G =700 мA; P _D =200 мВт; h ₂₁ =200400; f _T =250 МГц	SOT23.SOD23	
B6	BAT54A	ZOWIE	shd×2	V _R <30B; V _E (I _E =30 мA)<500 мВ; С _п <10 пФ; t _{RR} <5 нс	SOT23,SOD23	
B6s	BBY58-06W	INF	var	V _B <10B; I _F <20 mA; I _B <0.01 mKA; C _{1 B} =17.519.3 nΦ; C _{4 B} =5.56.6 nΦ	SOT323.SC70	
B7	2SB815B7	SANYO	ono	V _{GR0} =20 B; I _G =700 мА; P _D =200 мВт; h ₂₁ =300600; f _T =250 МГц	SOT23,SOD23	No. of the last of
B9	1SS311	TOSH	di	V _R <400 B; I _F <100 mA; V _F (I _F =100 mA)<1.2B; I _R <1.0 mKA	SOT346.SC59	
B 9	1SS397	TOSH	di	V _R <400 B; I _F <100 mA; V _F (I _F =100 mA)<1.3B	SOT323.SC70	
B9	2SC4617	ON	npn	V _{GB0} =50 B; I _C =100 MA; P _D =125 MBr; h ₂₁ =120560; f _Y =180 MFų	SOT416.SC75A	
BA	1SS154	TOSH	shd	V _B >6B; I _E <30 mA; V _E (I _E =10 mA)=0.5B; I _B <0.5 mкA	SOT346,SC59	
BA	BCW61A	ALLEG	ono	V _{CB0} =32B; I _{CB0} <20 HA; h ₂₁ =120220; V _{CE(set)} <0.25B	SOT23,SOD23	
BA	BCW61A	CDIL	ono	V _{CR0} =32B; I _C =200 MA; P _D =330 MBr; h ₂₁ =120220; f _T >180 MFu	SOT23,SOD23	160000000
BA	BCW61A	SAMS	ono	V _{CR0} =32B; I _C =100 MA; P _D =350 MBr; h ₂₁ =120220	SOT23,SOD23	100 /A DA
BA	BCW61A	ZETEX	ana	V _{CR0} =32B; I _C =200 мA; P _D =330 мBr; h ₂₁ =120220; f _T >180 MΓц	SOT23,SOD23	
BA	DAN217	ROHM	dix2	V _R <80 B; I _F <100 mA; P _D <200 mBT; V _F (I _F : 100 mA)<1.2 B	SOT346,SC59	
BAo	BCW61A	PHIL	ono	V _{CR0} =32B; I _C =200 MA; P _D =250 MBr; h ₂₁ =120220; f _T >100 MFu	SOT23,SOD23	
BAs	BCW61A	SIEM	ono	V _{C80} =32 B; I _C =100 mA; P _D =330 mBr; h ₂₁ =120220; f _T =250 MFu	SOT23,SOD23	100000000000000000000000000000000000000
BAt	BCW61A	PHIL	ono	V _{C80} =32 B; I _C =200 mA; P _D =250 mBr; h ₂₁ =120220; f _T >100 MFu	SOT23,SOD23	100000044720
BB	1SV128	TOSH	oin	V _B >50 B; I _E <50 mA; V _E (I _E =50 mA)=0.95 B; I _B <0.1 mrA	SOT346.SC59	110712 130
BB	2SB831B	REN	pnp	V _{C80} =25 B; I _C =700 mA; V _{C80} =150 mBr; h ₂₁ =85170	SOT23,SOD23	
BB	BCW61B	ALLEG	ono	V _{C80} -23B; I _{C80} <20 HA; h ₂₁ =180310; V _{CB(st)} <0.25 B	SOT23,SOD23	
BB	BCW61B	CDIL			SOT23,SOD23	
BB BB	000000000000000000000000000000000000000	SAMS	pnp	V _{CBO} =32 B; I _C =200 мА; P _D =330 мВт; h ₂₁ =180310; f _T > 180 МГц	SOT23,SOD23	-
BB	BCW61B BCW61B	ZETEX	pnp	V _{CB0} =32B; I _C =100 mA; P _D =350 mBr; h ₂₁ =180310	SOT23,SOD23	100000000000000000000000000000000000000
BBo			pnp	V _{G80} =32B; I _C =200 мА; P _D =330 мВг; h ₂₁ =180310; f _T >180 МГц		1000000000
	BCW61B	PHIL	pnp	V _{GBO} =32 B; I _C =200 мA; P _D =250 мBт; h ₂₁ =180310; f _T >100 МГц	SOT23,SOD23	100000 000
BBs	BCW61B	SIEM	pnp	V _{CB0} =32 B; I _C =100 MA; P _D =330 MBr; h ₂₁ =180310; f _T =250 MFц	SOT23,SOD23	
BBt	BCW61B	PHIL	pnp	V _{CB0} =32 B; I _C =200 MA; P _D =250 MBr; h ₂₁ =180310; f _T >100 MF _L	SOT23,SOD23	
BBU	2SD2114KU	ROHM	npn	V _{GB0} =25B; I _C =500 мA; P _D =200 мBr; h ₂₁ =5601200; f _T >350 МГц	SOT346,SC59	200000000000000000000000000000000000000
BBV	2SD2114KV	ROHM	npn	V _{CB0} =25B; I _C =500 мA; P _D =200 мBт; h ₂₁ =8201800; f _T >350 МГц	SOT346,SC59	10000000
BBW	2SD2114KW	ROHM	npn	V _{CB0} =25B; I _C =500 мA; P _D =200 мBτ; h ₂₁ =12002700; f _T >350 MΓц	SOT346,SC59	100000000
BC	2SB831C	REN	pnp	V _{GB0} =25B; I _C =700 MA; P _D =150 MBr; h ₂₁ =120240	SOT23,SOD23	200000 02
BC	BCW61C	ALLEG	pnp	V _{CB0} =32B; I _{CB0} <20 HA; h ₂₁ =250460; V _{CE(sat)} <0.25B	SOT23,SOD23	
BC	BCW61C	CDIL	pnp	V_{GB0} =32 B; I_C =200 MA; P_D =330 MBT; h_{21} =250460; f_T >180 MFU	SOT23,SOD23	
BC	BCW61C	SAMS	pnp	V_{CB0} =32 B; I_C =100 MA; P_D =350 MBT; h_{21} =250460; f_T >125 MF I_T	SOT23,SOD23	
BC	BCW61C	ZETEX	pnp	V _{CB0} =32 B; I _C =200 MA; P _D =330 MBr; h ₂₁ =250460; f _T >180 MF _U	SOT23,SOD23	
BCp	BCW61C	PHIL	pnp	V_{CB0} =32 B; I_C =200 mA; P_D =250 mBT; h_{21} =250460; f_T >100 M Γ_U	SOT23,SOD23	100000110915
BCs	BCW61C	SIEM	pnp	V _{CB0} =32 B; I _C =100 мA; P _D =330 мВт; h ₂₁ =250460; f ₁ =250 МГц	SOT23,SOD23	0.0000000000000000000000000000000000000
BCt	BCW61C	PHIL	pnp	V_{CB0} =32 B; I_C =200 mA; P_0 =250 mBr; h_{21} =250460; f_T >100 M Γ_{LL}	SOT23,SOD23	
BD	1SS271	TOSH	shd×2	V _R >6B; I _F <30 мA; V _F (I _F =10 мA)=0.5B; I _R <0.5 мкA	SOT346,SC59	
BD	BCW61D	ALLEG	pnp	V _{CB0} =32B; I _{CB0} <20 нA; h ₂₁ =380630; V _{CE(sat)} <0.25 B	SOT23,SOD23	
BD	BCW61D	CDIL	pnp	V_{C80} =32 B; I_C =200 mA; P_D =330 mBr; h_{21} =380630; f_T >180 M Γ_U	SOT23,SOD23	
BD	BCW61D	SAMS	pnp	V _{CB0} =32 B; I _C =100 мА; P _D =350 мВт; h ₂₁ =380630; f _T >125 МГц	SOT23,SOD23	1.00
BD	BCW61D	ZETEX	pnp	V _{CB0} =32 B; I _C =200 мA; P _D =330 мВт; h ₂₁ =380630; f _T > 180 МГц	SOT23,SOD23	T1077
BDM	2SA1733KM	ROHM	pnp	V _{CB0} =30 B; I _C =30 мA; P ₀ =200 мВт; h ₂₁ =3982; f _T >400 МГц	SOT346,SC59	WG377 - 65
BDM	2SA1808M	ROHM	pnp	V _{CB0} =30 B; I _C =30 мА; P ₀ =200 мВт; h ₂₁ =3982; f _T >400 МГц	SOT323,SC70	10.000 30
BDN	2SA1733KN	ROHM	pnp	V_{C80} =30 B; I_C =30 MA; P_0 =200 MBT; h_{21} =56120; f_T >400 MF $_{4}$	SOT346,SC59	
BDN	2SA1808N	ROHM	pnp	V _{CB0} =30 B; I _C =30 мA; P ₀ =200 мВт; h ₂₁ =56120; f _T >400 МГц	SOT323,SC70	
BDP	2SA1733KP	ROHM	pnp	V_{C80} =30 B; I_C =30 mA; P_D =200 mBT; h_{21} =82180; f_T >400 M Γ_U	SOT346,SC59	
BDP	2SA1808P	ROHM	pnp	V_{C80} =30 B; I_C =30 mA; P_D =200 mBT; h_{21} =82180; f_T >400 M Γ_H	SOT323,SC70	B·E·C
BDp	BCW61D	PHIL	pnp	V_{CB0} =32 B; I_C =200 mA; P_D =250 mBr; h_{21} =380630; f_T >100 M Γ_{II}	SOT23,SOD23	100000000000000000000000000000000000000
BDs	BCW61D	SIEM	pnp	V _{G80} =32B; I _C =100 мА; P _D =330 мВт; h ₂₁ =380630; f _T =250 МГц	SOT23,SOD23	B·E·C





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
BDt	BCW61D	PHIL	pnp	V _{CR0} =32 B; I _C =200 mA; P _D =250 mBT; h ₂₁ =380630; f _T >100 MFu,	SOT23,SOD23	B·E·C
BE	1SV172	TOSH	pin×2	V _B >50 B; I _E <50 mA; V _E (I _E =50 mA)=0.95 B; I _B <0.1 mkA	SOT346,SC59	A1 · K2 · K1,A2
BE	1SV252	TOSH	pin×2	V _B >50 B; I _E <50 mA; V _E (I _E =50 mA)<0.98 B; I _B <0.1 mkA	SOT323,SC70	A1 · K2 · K1, A2
BE2	MMBZ5221ELT1	ON	dz	V ₂ (I ₂₇ =20 mA)=2.282.52 B; I _B <100 mrA	SOT23.SOD23	A·n.c.·K
BE7	MMBZ5226ELT1	ON	dz	V ₂ (I ₂₇ =20 mA)=3.133.47 B; I _B <25 mkA	SOT23,SOD23	A·n.c.·K
BE9	MMBZ5228ELT1	ON	dz	V _x (I _{zz} =20 mA)=3.704.10 B; I _B <10 mcA	SOT23,SOD23	145.000.000.000
BF	1SS268	TOSH	di×2	V _B >30 B; I _E <50 mA; V _E (I _E =2 mA)<0.85 B; I _B <0.1 mkA	SOT346,SC59	
BF	1SS312	TOSH	di	V _B <30 B; I _F <50 mA; V _F (I _F =2 mA)<0.85 B; I _B <0.1 mkA	SOT323,SC70	
BF	1SS364	TOSH	di×2	V _R <30B; I _F <50 mA; V _F (I _F =2 mA)<0.85 B; I _R <0.1 mkA	SOT416.SC75A	
BF	KDS112	KEC	di×2	V _R =30B; I _C =50 мА; I _R =0.1 мкА; С _T =0.8 пФ	SOT323,SC70	-
BF1	MMBZ5229ELT1	ON	dz	V _x (I _{zz} =20 mA)=4.084.52 B; I _B <5 mkA	SOT23,SOD23	
BF2	MMBZ5230ELT1	ON	dz	V _x (I _{zz} =20 mA)=4.464.94 B; I _B <5 mkA	SOT23.SOD23	1901
BF3	MMBZ5231ELT1	ON	dz	V ₂ (I _{2T} =20 mA)=4.845.36 B; I _R <5 mkA	SOT23.SOD23	Contract Con
BF4	MMBZ5232ELT1	ON	dz	V _x (I _{zz} =20 mA)=5.325.88 B; I _R <5 mkA	SOT23.SOD23	1000-000-000-000-000-000-000-000-000-00
BF6	MMBZ5234ELT1	ON	dz	V _X (I ₇₇ =20 MA)=5.896.51 B; I _R <5 MKA	SOT23,SOD23	5/20/2003/00/00/00/00
BF7	MMBZ5235ELT1	ON	dz	V _Z (I _{ZT} =20 MA)=6.467.14 B; I _R <3 MKA	SOT23,SOD23	
BF8	MMBZ5236ELT1	ON	dz	V _x (I _{zz} =20 MA)=7.127.88 B; I _e <3 MKA	SOT23,SOD23	
BF9	MMBZ5237ELT1	ON	dz	V _X (I _{ZT} =20 MA)=7.798.61 B; I _R <3 MKA	SOT23,SOD23	
BFR	2SC4642KR	ROHM	non	V _{CR0} =50 B; I _C =100 mA; P _D =200 mB; I _D =180390; f _T >180 MFu		The second secon
BFR	2SC4042RM 2SC4723R	ROHM	non		SOT346,SC59 SOT323.SC70	10.17.55
		1.033.220	1	V _{CBO} =50 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =180390; f _T >180 МГц		127.50.00
BFS	2SC4642KS	ROHM	npn	V _{CB0} =50 B; I _C =100мA; P _D =200мВт; h ₂₁ =270560; f _T >180 МГц	SOT346,SC59	
BFS	2SC4723S	ROHM	npn	V _{CB0} =50 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =270560; f _T >180 МГц	SOT323,SC70	
BFs	BCW61FF	SIEM	pnp	V _{CB0} =32B; I _C =100мA; P _D =330мBт; h ₂₁ =250460; f _T =250МГц	SOT23,SOD23	
BG	1SS269	TOSH	di×2	V _R >30 B; I _F <50 mA; V _F (I _F =2 mA) < 0.85 B; I _R <0.1 mkA	SOT346,SC59	
BG	1SS313	TOSH	di	$V_R \le 30 B$; $I_F \le 50 \text{ mA}$; $V_F \{I_F = 2 \text{ mA}\} \le 0.85 B$; $I_R \le 0.1 \text{ mKA}$	SOT323,SC70	102000012000
BG	BCX71G	ALLEG	pnp	V _{CB0} =45B; I _{CB0} <20 HA; h ₂₁ =120220; V _{CE[sat]} <0.25B	SOT23,SOD23	T017171
BG	BCX71G	CDIL	pnp	V _{CB0} =45B; I _C =200мA; P _D =250мBт; h ₂₁ =120220; f _T >100МГц	SOT23,SOD23	
BG	BCX71G	SAMS	pnp	V _{CB0} =45 B; I _C = 100 mA; P _D =350 mBr; h ₂₁ =120220	SOT23,SOD23	
BG	BCX71G	ZETEX	pnp	V _{CB0} =45 B; I _C =200 мА; P _D =330 мВт; h ₂₁ =120220; f _T > 180 МГц	SOT23,SOD23	
BG	BRC144ECM	REN	Dnpn	V_{CC} =50 B; I_{OUT} =100 mA; P_D =150 mBT; h_{21} >70; 47 к/47 к	SOT323,SC70	
BG	BRC144EMP	REN	Dnpn	V_{CC} =50 B; I_{OUT} =100 mA; P_D =150 mBT; h_{21} >70; 47 к/47 к	SOT23,SOD23	10000001000
BG2	MMBZ5239ELT1	ON	dz	V _Z (I _{ZT} =20 mA)=8.659.56 B; I _R <3 mкA	SOT23,SOD23	100000000000000000000000000000000000000
BG3	MMBZ5240ELT1	ON	dz	V _z (I _{ZT} =20 mA)=9.510.5 B; I _R <3 mkA	SOT23,SOD23	A·n.c.·K
BG5	MMBZ5242ELT1	ON	dz	V _Z (I _{ZT} =20 mA)=11.412.6 B; I _R <1 mkA	SOT23,SOD23	A·n.c.·K
BG6	MMBZ5243ELT1	ON	dz	V ₂ (I _{ZT} =9.5 мA)= 12.3513.65 B; I _R <0.5 мкA	SOT23,SOD23	A·n.c.·K
BG7	MMBZ5244ELT1	ON	dz	V ₂ (I _{ZT} =8.5 mA}=13.3014.70 B; I _R <0.1 mkA	SOT23,SOD23	A·n.c.·K
BG8	MMBZ5245ELT1	ON	dz	V _Z (I _{ZT} =8.5 mA)=14.2515.75B; I _R <0.1 mKA	SOT23,SOD23	Arn.c.+K
BG9	MMBZ5246ELT1	ON	dz	V ₂ (I _{ZT} =7.8 mA)=15.216.8 B; I _B <0.1 mкA	SOT23,SOD23	A·n.c.·K
BGp	BCX71G	PHIL	pnp	V _{CB0} =45B; I _C =200 мA; P ₀ =250 мВт; h ₂₁ =120220; f ₁ >100 МГц	SOT23,SOD23	B·E·C
BGs	BCX71G	SIEM	pnp	V _{CB0} =45B; I _C =100мA; P _D =330мBт; h ₂₁ =120220; f _T =250МГц	SOT23,SOD23	B-E-C
BGt	BCX71G	PHIL	pnp	V _{GB0} =45B; I _G =200мA; P _B =250мВт; h ₂₁ =120220; f _T >100МГц	SOT23,SOD23	
ВН	1SS295	TOSH	shd×2	V _B >4B; I _F <30 mA; V _F (I _F =2 mA)=0.32 B; I _B <25 mkA	SOT346,SC59	A1-K2-K1,A2
ВН	1SS350	SANYO	shd	V _B >5B; V _E (I _E =1 mA)<0.23B; I _E (V _B =0.5B)<25 mKA	SOT23,SOD23	A·n.c·K
ВН	BCX71H	ALLEG	onp	V _{CB0} =45B; I _{CB0} <20 HA; h ₂₁ =180310; V _{CB1sttl} <0.25B	SOT23,SOD23	2.010
ВН	BCX71H	CDIL	pnp	V _{CR0} =45B; I _C =200 мA; P _D =250 мВт; h ₂₁ =180310; f _T >100 МГц	SOT23,SOD23	100.00301001
ВН	BCX71H	SAMS	pnp	V _{CB0} =45B; I _C =100 mA; P _D =350 mBT; h ₂₁ =140310	SOT23,SOD23	10.666
BH	BCX71H	ZETEX	ono	V _{CBB} :45B; I _C :200мA; P _B :330мBr; h ₂₁ :180310; f _T >180МГц	SOT23.SOD23	
BH2	MMBZ5248ELT1	ON	dz	V _x (I _{zz} =7.0 mA)=17.118.9B; I _B <0.1 mkA	SOT23,SOD23	
BH4	MMBZ5250ELT1	ON	dz	V _A (I _{2T} =6.2 mA)=19.021.0B; I _B <01 mKA	SOT23,SOD23	
BH6	MMBZ5252ELT1	ON	dz	V _Z (I _{ZT} =5.2 mA)=22.825.2 B ₁ I _R <0.1 mkA	SOT23,SOD23	
BH7	MMBZ5252ELT1	ON	dz	V _Z (I _{ZT} =5.0 mA)=23.7526.25B; I _R <0.1 mkA	SOT23,SOD23	
au.	MMBZ5253ELT1	ON	dz	V _Z (_{ZT} =0.0 MA)=25.7520.25 B, I _R <0.1 MKA V _Z (_{ZT} =5.0 MA)=25.6528.35 B; I _R <0.1 MKA	SOT23,SOD23	100000000000000000000000000000000000000

SOT490 TESM VMT3 1 SOT523 SOT323 SOT23-3 1 SOT523 SOT324 SOD23-3 1 SOT523 SOT346 SOD23-3 1 SOT523 SOT523 SOT525 SO

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
3H9	MMBZ5255ELT1	ON	dz	V _Z (I _{ZT} =4.5 mA)=26.629.4 B; I _R <0.1 mkA	SOT23,SOD23	A·n.c.·K
BHM	2SC4699KM	ROHM	npn	V _{гал} = 25 B; I _с = 200 мА; P _п = 200 мВт; h ₂₁ = 3982; f _T > 250 МГц	SOT346,SC59	B-E-C
BHM	2SC4700M	ROHM	npn	V ₀₈₀ =25B; I _C =200 мA; P _D =150 мВт; h ₂₁ =3982; f _T >250 МГц	SOT323.SC70	B-E-C
BHN	2SC4699KN	ROHM	non	V _{csn} =25B; I _c =200 мA; P _n =200 мВт; h ₂₁ =56120; f _T > 250 МГц	SOT346.SC59	B-E-C
BHN	2SC4700N	ROHM	npn	V _{CR0} =25 B; I _C =200 мA; P _D =150 мВт; h ₂₁ =56120; f _T >250 МГц	SOT323,SC70	
BHP	2SC4699KP	ROHM	non	V _{D80} =25 B; I _C =200 мА; P _D =200 мВт; h ₂₁ =82180; f _T >250 МГц	SOT346.SC59	
3HP	2SC4700P	ROHM	npn	V _{CB0} =25 B; I _C =200 мA; P _D =150 мВт; h ₂₁ =82180; f _T >250 МГц	SOT323,SC70	B·E·C
ЗНо	BCX71H	PHIL	ono	V _{CR0} =45 B; I _C =200 mA; P _D =250 mBt; h ₂₁ =180310; f _T >100 MFu	SOT23,SOD23	
BHs	BCX71H	SIEM	pnp	V _{G80} =45B; I _C =100 мA; P _D =330 мВт; h ₂₁ =180310; f _T =250 МГц	SOT23,SOD23	
BHt	BCX71H	PHIL	pnp	V _{G80} =45B; I _G =200 MA; P _D =250 MBr; h ₂₁ =180310; f ₁ >100 MFu	SOT23,SOD23	
3J	BCX71J	ALLEG	ono	V _{C80} =45B; I _{C80} <20 HA; h ₂₁ =250460; V _{CF(set)} <0.25B	SOT23,SOD23	
3J	BCX71J	CDIL	ono	V _{G80} =45 B; I _G =200 MA; P _D =250 MBr; h ₂₁ =250460; f _T >100 MFu	SOT23,SOD23	
3J	BCX71J	SAMS	ono	V _{C80} =45B; I _C =100 mA; P _D =350 mBr; h ₂₁ =250460	SOT23,SOD23	
3J	BCX71J	ZETEX	ono	V ₀₈₀ =45 B; I _C =200 MA; P _D =330 MBr; h ₂₁ =250460; f _T >180 MFu	SOT23,SOD23	100000000000000000000000000000000000000
3J1	MMBZ5256ELT1	ON	dz	V ₂ (I _{2T} =4.2 mA)=28.531.5B; I _R <0.1 mKA	SOT23,SOD23	
J2	MMBZ5257ELT1	ON	dz	V ₂ (I _{2T} =3.8 mA)=31.3534.65B; I _B <0.1 mkA	SOT23,SOD23	
3J3	MMBZ5258ELT1	ON	dz	V ₂ (I _{2T} =3.4 mA)=34.237.8 B; I _R <0.1 mkA	SOT23,SOD23	
3J7	MMBZ5262ELT1	ON	dz	V ₂ (I _{2T} =3.4 MA)=34.237.0 B, I _R < 0.1 MKA V ₂ (I _{2T} =2.5 MA)=48.4553.55B; I _R < 0.1 MKA	SOT23,30D23	
		ON				100.000
IJ8	MMBZ5263ELT1	PHIL	dz	V ₂ (I _{ZT} =2.2 mA)=53.2058.80B; I _R <0.1 mKA	SOT23,SOD23	120 100 100 100 100
Np.	BCX71J		pnp	V _{CB0} =45B; I _C =200 мА; P _D =250 мВт; h ₂₁ =250460; f _T >100 МГц	SOT23,SOD23	
Js	BCX71J	SIEM	pnp	V _{C80} =45 B; I _C =100 мА; P ₀ =330 мВт; h ₂₁ =250460; f _T =250 МГц	SOT23,SOD23	
IJt	BCX71J	PHIL	pnp	V _{C80} =45B; I _C =200 mA; P _D =250 mBr; h ₂₁ =250460; f _T >100 MFц	SOT23,SOD23	
JU	2SD2226KU	ROHM	npn	V_{C80} =60 B; I_C =150 MA; P_D =200 MBT; h_{21} =5601200; f_T >250 MF $_{II}$	SOT346,SC59	
3JU	2SD2351U	ROHM	npn	V_{C80} =60 B; I_C =150 mA; P_0 =200 mBr; h_{21} =5601200; f_T >250 M Γ_{IJ}	SOT323,SC70	
JV	2SD2226KV	ROHM	npn	V_{GB0} =60 B; I_C =150 mA; P_D =200 mBr; h_{21} =8201800; f_T >250 M Γ_{IL}	SOT346,SC59	
3JV	2SD2351V	ROHM	npn	V _{GB0} =60 B; I _C =150 мA; P _D =200 мВт; h ₂₁ =8201800; f _T >250 МГц	SOT323,SC70	777.7
JW.	2SD2226KW	ROHM	npn	V _{CB0} =60 B; I _C =150 мA; P _D =200 мВт; h ₂₁ =12002700; f _T >250 МГц	SOT346,SC59	
3JW	2SD2351W	ROHM	npn	V_{CB0} =60 В; I_C =150 мА; P_D =200 мВт; h_{21} =12002700; f_T >250 МГц	SOT323,SC70	
3K	BCX71K	ALLEG	pnp	V _{CB0} =45B; I _{CB0} <20 нА; h ₂₁ =380630; V _{CE(sat)} <0.25B	SOT23,SOD23	
3K	BCX71K	CDIL	pnp	V_{C80} =45B; I_C =200 MA; P_D =250 MBT; h_{21} =380630; f_T >100 M Γ_{IJ}	SOT23,SOD23	
3K	BCX71K	SAMS	pnp	V _{CB0} =45 B; I _C =100 мA; P _D =350 мВт; h ₂₁ =380630	SOT23,SOD23	1000000
3K	BCX71K	ZETEX	onp	V_{C80} =45B; I_C =200 MA; P_D =330 MBT; h_{21} =380630; f_T >180 M Γ_{II}	SOT23,SOD23	
3K1	MMBZ5265ELT1	ON	dz	V _Z (I _{ZT} =2 mA)=58.9065.10 B; I _R <0.1 mrA	SOT23,SOD23	A·n.c.·K
3Ко	BCX71K	PHIL	pnp	V_{G80} =45B; I_C =200 mA; P_D =250 mBt; h_{21} =380630; f_T >100 MFu,	SOT23,SOD23	B-E-C
3Ks	BCX71K	SIEM	pnp	V _{C80} =45 B; I _C =100 мA; P _D =330 мВт; h ₂₁ =380630; f _T =250 МГц	SOT23,SOD23	B·E·C
3Kt	BCX71K	PHIL	pnp	V_{C80} *45B; I_C *200 mA; P_0 *250 mBr; h_{21} *380630; f_T >100 M Γ_U	SOT23,SOD23	B·E·C
BLL	2SC4771KL	ROHM	npn	V_{CB0} =30 B; I_C =50 mA; P_0 =200 mBT; h_{21} =2756; f_T >600 MFu	SOT346,SC59	B.E.C
BLL	2SC4772L	ROHM	npn	V_{CB0} =30 B; I_C =50 mA; P_D =150 mBT; h_{21} =2756; f_T >600 M Γ_{II}	SOT323,SC70	B-E-C
BLM	2SC4771KM	ROHM	npn	V _{CB0} =30 B; I _C =50 мA; P ₀ =200 мВт; h ₂₁ =3982; f _T >600 МГц	SOT346,SC59	B·E·C
BLM	2SC4772M	ROHM	npn	V _{G80} =30 B; I _C =50 mA; P _D =150 mBT; h ₂₁ =3982; f _T >600 MFu	SOT323,SC70	B·E·C
BLN	2SC4771KN	ROHM	npn	V _{GB0} =30 B; I _C =50 mA; P _D =200 mBT; h ₂₁ =56120; f _T >600 MFц	SOT346,SC59	B·E·C
BLN	2SC4772N	ROHM	npn	V _{G80} =30 B; I _G =50 mA; P _B =150 mBr; h ₂₁ =56120; f _T >600 MFu	SOT323,SC70	B·E·C
BLP	2SC4771KP	ROHM	npn	$V_{G80}=30B$; $I_{C}=50$ mA; $P_{D}=200$ mBT; $h_{21}=82180$; $f_{T}>600$ MF I_{L}	SOT346,SC59	B·E·C
LP	2SC4772P	ROHM	npn	V _{G80} =30 B; I _G =50 mA; P _D =150 mBT; h ₂₁ =82180; f _T >600 MFu	SOT323,SC70	B·E·C
BM	BSS63L	MOT	pnp	V _{GB0} =100 B; I _G =800 мА; P _D =330 мВт; h _{E1} >30; f _T =150 МГц	SOT23,SOD23	100000000000000000000000000000000000000
Мр	BSS63	PHIL	ono	V _{G80} =110 B; I _C =100 мА; P _D =250 мВт; h ₂₁ >30; f _T >50 МГц	SOT23,SOD23	VS5377 373
MQ	2SC4713KQ	ROHM	non	V ₀₈₀ =12B; I _C =50мA; P _D =200мВт; h ₂₁ =120270; f _T =800МГц	SOT346.SC59	100000000000000000000000000000000000000
MQ	2SC4774Q	ROHM	ngn	V _{CB0} =12B; I _C =50 мA; P _D =150 мВт; h ₂₁ =120270; f _T =800МГц	SOT323.SC70	
MR	2SC4713KR	ROHM	npn	V _{сво} =12B; I _C =50мA; P _D =200 мВт; h ₂₁ =180390; f _T =800МГц	SOT346,SC59	
MR.	2SC4774R	ROHM	npn	V ₀₈₀ =12B; I _C =50мA; P _D =150 мВт; h ₂₁ =180390; f _T =800МГц	SOT323,SC70	
BMS	2SC4713KS	ROHM	npn	V _{C80} =12B; I _C =50 MA; P _D =200 MBT; h ₂₁ =270560; f _T =800 MFu	SOT346,SC59	
BMS	2SC4774S	ROHM	npn	V _{CR0} =12B; I _C =50MA; P _D =150 MBT; h ₂₁ =270560; f _T =800MFu	SOT323,SC70	10.55





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
BMs	BSS63	SIEM	pnp	V _{CB0} =100 B; I _C =800 мА; P _D =330 мВт; h ₂₁ >30; f ₇ =150 МГц	SOT23,SOD23	B·E·C
BMt	BSS63	PHIL	prip	V _{сво} =110B; I _c =100 мА; Р _о =250 мВт; h ₂₁ >30; f _T >50 МГц	SOT23,SOD23	B·E·C
BN	2SK3290	REN	nMOS	V _{DS} =30B; I _D =500 мА; P _D =400 мВт; R _{DS(on)} < 1.25 Ом	SOT23,SOD23	G·S·D
BNs	BCW61FN	SIEM	pnp	V _{сво} =32B; I _с =100 мА; P _о =330 мВт; h ₂₁ =380630; f _T =250 МГц	SOT23.SOD23	B-E-C
30	BCW61AR	PHIL	pnp	V _{сво} =32B; I _с =200 мА; P _о =250 мВт; h ₂₁ =120220; f _T >100МГц	SOT23,SOD23	B·E·C
BP	2SJ574	REN	oMOS	V _{DS} =30B; I _D =300 мА; P _D =400 мВт; R _{DS(m)} < 3.1 Ом	SOT23.SOD23	100000000000000000000000000000000000000
BQ	2PB709AQ	PHIL	onp	V _{CR0} =45 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ =160260; f _T >70 МГц	SOT346,SC59	B·E·C
BQ	2SC2412KQ	ROHM	non	V _{CR0} =50 B; I _C =150 мА; Р _П =200 мВт; h ₂₁ =120270; f _T >180 МГц	SOT346,SC59	
BQ	2SC2412KQLT1	LRC	non	V _{CB0} =60 B; I _C =150 мА; P _D =200 мВт; h ₂₁ =120270; f _T =180 МГц	SOT23.SOD23	
BQ.	2SC4081Q	ROHM	non	V _{CB0} =50 B; I _C =150 MA; P _D =200 MBr; h ₂₁ =120270; f _T >180 MFц	SOT323,SC70	
3Q	2SC4617	ROHM	non	V _{CR0} =50 B; I _C =150 MA; P _D =260 MB1; I _{D1} =120270; I _T >180 MF _U	S0T416,SC75A	
BQ	2SC5658Q	ROHM	non	0.00	VMT3.VMD3	B·E·C
BR		PHIL	1	V _{C80} =60 B; I _C =150 MA; P _D =150 MBT; h ₂₁ =120270; f _T >180 MFц	SOT346.SC59	0.5000000000
BR BR	2PB709AR		pnp	V _{CB0} =45B; I _C =100мA; P ₀ =250мBr; h ₂₁ =290460; f ₁ >80МГц		000000000000000000000000000000000000000
	2SC2412KR	ROHM	npn	V _{CB0} =50 B; I _C =150 mA; P _D =200 mBr; h ₂₁ =180390; f _T >180 MFц	S0T346,SC59	
BR	2SC2412KRLT1	LRC	npn	V _{CB0} =60 B; I _C =150 MA; P _D =200 MBT; h ₂₁ =180390; f _T =180 MFu	SOT23,SOD23	
BR	2SC4081R	ROHM	npn	V _{CB0} =50 B; I _C =150 MA; P _D =200 MBT; h ₂₁ =180390; f _T >180 MFц	S0T323,SC70	
BR	2SC4617	ROHM	npn	V _{C80} =50 B; I _C = 150 мA; P _D = 150 мBт; h ₂₁ = 180390; f _T > 180 МГц	SOT416,SC75A	
BR	2SC5658R	ROHM	npn	V _{CB0} =60 B; I _C =150 мА; P _D =150 мВт; h ₂₁ =180390; f _T >180 МГц	VMT3,VMD3	B.E.C
3R	BCW60DR	ZETEX	npn	V_{CB0} =32B; I_C =200 mA; P_D =330 mBT; h_{21} =380630; f_T >250 MFu,	SOT23,SOD23	
BR	MSB1218ART1	MOT	pnp	V _{CB0} =45B; I _C =100 мA; P _D =150 мВт; h ₂₁ =210340	SOT323,SC70	
BS	2PB709AS	PHIL	pnp	V _{CB0} =45B; I _C =100 мА; P _D =250 мВт; h ₂₁ =160260; f _T >60 МГц	SOT346,SC59	B·E·C
BS	2SC2412KS	ROHM	npn	V_{CB0} =50 B; I_C =150 mA; P_D =200 mBT; h_{21} =270560; f_T >180 M Γ_{II}	SOT346,SC59	B·E·C
BS	2SC2412KSLT1	LRC	npn	V _{CB0} =60 B; I _C = 150 мА; P _D =200 мВт; h ₂₁ =270560; f _T = 180 МГц	SOT23,SOD23	B·E·C
BS	2SC4081S	ROHM	non	V _{CB0} =50 B; I _C =150 мА; P _D =200 мВт; h ₂₁ =270560; f _T > 180 МГц	SOT323,SC70	B·E·C
BS	2SC4617	ROHM	non	V _{CB0} =50 B; I _C = 150 мА; P _D = 150 мВт; h ₂₁ = 270560; f _T > 180 МГц	SOT416,SC75A	B·E·C
BS	2SC5658S	ROHM	non	V _{CB0} =60 B; I _C =150 мA; P _D =150 мBт; h ₂₁ =270560; f _T >180 МГц	VMT3,VMD3	B·E·C
BS	MSB1218AST1	MOT	pnp	V _{CB0} =45 B; I _C =100 mA; P _D =150 mBT; h ₂₁ =290460	SOT323,SC70	B·E·C
BSA	BC848AU	AUK	npn	V _{CB0} =30 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =110220; f _T =150 МГц	SOT323,SC70	B·E·C
BSA	BC848AUF	AUK	npn	V _{сво} =30B; I _с =100 мА; P _о =200 мВт; h ₂₁ =110220; f _T =150 МГц	SOT323,SC70	B·E·C
BSB	BC848BU	AUK	non	V _{CR0} =30 B; I _C =100 mA; P _D =200 mBT; h ₂₁ =200450; f _T =150 MFu,	SOT323,SC70	B·E·C
BSB	BC848BUF	AUK	non	V _{свп} =30 B; I _с = 100 мА; P _п =200 мВт; h ₂₁ =200450; f _T =150 МГц	SOT323,SC70	B·E·C
BSC	BC848CU	AUK	non	V _{CBD} =30B; I _C =100 мA; P _D =200 мВт; h ₂₁ =420800; f _T =150 МГц	SOT323,SC70	B·E·C
BSC	BC848CUF	AUK	non	V _{CR0} =30 B; I _C =100 mA; P _D =200 mBT; h ₂₁ =420800; f _T =150 MFu	SOT323,SC70	
BV	1SV247	SANYO	oin	V _B >50B; I _E <50 mA; V _E (I _E =50 mA)=0.95B; I _B <0.1 mkA	SOT323.SC70	
2	IRLML6302	IR		HEXFET, V _{DS} =20 B; I _D =0.62 A; P _D =540 MBT; R _{DS(on)} <0.9 OM	SOT23,SOD23	
00	HSMS2820	HP	shd	V _{BB} > 15B; V _E (I _E =30 мA) < 0.7B; I _B (V _B =1B) < 100 нA; C _D <1.0 пФ	SOT23,SOD23	
00	HSMS282B	HP	shd	V _{pp} >15B; V _e (I _c =30 мA) < 0.7B; I _p (V _p =1B) < 100 μA; C _T <1.0 πΦ; R _n =12 0м	SOT323.SC70	
00	BCW29	ALLEG	pnp	V _{CB0} =30 B; I _{CB0} <100 HA; h ₂₁ =120260; V _{CB1sal} <0.3 B	SOT23.SOD23	
21	BCW29	CDIL		V _{CB0} =30 B, I _{CB0} <100 HA, I _{D1} =120260, V _{CE(sat)} <0.3 B V _{CB0} =30 B, I _C =100 MA; P _D =330 MBT; h ₂₁ =120260; f _T >150 MΓц	SOT23,SOD23	20000000
01	BCW29	SAMS	pnp		SOT23,SOD23	
	200000000000000000000000000000000000000		pnp	V _{CBO} =30B; I _C =100mA; P _D =350mBr; h ₂₁ =120260		
01	BCW29	ZETEX	pnp	V _{CB0} =30 B; I _C =100 MA; P _D =330 MBτ; h ₂₁ =120260; f _T >150 MΓι ₄	SOT23,SOD23	
01	HSMS2821		shd	V _{BR} >15B; V _E (I _F =30 MA)<0.7B; I _R (V _R =1B)<100 HA; C _U <1.0 nΦ	SOT23,SOD23	
01	MMBZ5221BT	DIODS	dz	V _Z (I _{ZT} =20 mA)= 2.282.52 B; I _R <100 mkA	SOT523	A•n.c.•K
21	SST111	SIL	nFET	V _{6S} =35B; P _D =350 MBT; I _{DSS} >20 MA; R _{DS(m)} <30 OM	SOT23,SOD23	100000
CIA	CMPT3904	CSI	non	V _{CB0} =60 B; I _C =200 мА; P _D =350 мВт; h ₂₁ =100300; f _T >300 МГц	SOT23,SOD23	
CID	CMPTA42	CSI	npn	V _{CBO} =300 B; I _C =500 мA; P _D =350 мВт; h ₂₁ >40; f _T >50 МГц	SOT23,SOD23	
CIG	CMPTA06	CSI	npn	V _{CB0} =80 B; I _C =500 мА; P ₀ =350 мВт; h ₂₁ >50; f _T >100 МГц	SOT23,SOD23	
CIG	KSA1623	SAMS	npn	V _{CB0} =60 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =200400; f _T >250 МГц	SOT23,SOD23	
CIJ	CMPT2369	CSI	npn	V_{CB0} =40 B; I_C =500 mA; P_D =350 mBT; h_{21} =40120; f_T >500 M Γ_U	SOT23,SOD23	200000000000000000000000000000000000000
C1K	CMPT6428	CSI	non	V_{CB0} =60 B; I_C =200 mA; P_D =350 mBT; h_{21} =250650; f_T =100700 MF μ	SOT23,SOD23	B·E·C
C1L	CMPT6429	CSI	non	V _{CB0} =55B; I _C =200 MA; P _D =350 MBT; h ₂₁ =5001250; f _T =100700 MF _U	SOT23,SOD23	B.E.C
CIL	KSA1623	SAMS	non	V _{CR0} =60 B; I _C =100 mA; P _D =200 mBT; h ₂₁ =300600; f _T >250 MFu	SOT23,SOD23	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
C1M	CMPTA13	CSI	npn	V _{G80} =30 B; I _C =500 мА; P _D =350 мВт; h ₂₁ > 5000; f _T > 125 МГц	SOT23,SOD23	B-E-C
CIN	CMPTA14	CSI	npn	V_{G80} =30 B; I_C =500 mA; P_D =350 mBr; h_{21} >10000; f_T >125 M Γ_{II}	SOT23,SOD23	B·E·C
210	KSA1623	SAMS	npn	$V_{G80}=60 \text{ B; } I_C=100 \text{ mA; } P_0=200 \text{ mBr; } h_{21}=90180; f_T>250 \text{ MFц}$	SOT23,SOD23	B·E·C
C1p	BCW29	PHIL	pnp	V _{CR0} =32 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =120260; f _T >100 MFu	SOT23,SOD23	B·E·C
CIP	CMPT2222A	CSI	npn	V _{сво} : 75 B; I _C : 600 мA; P _D : 350 мВт; h ₂₁ < 35; f _T > 300 МГц	SOT23,SOD23	B-amp-C
CIQ	CMPT5088	CSI	npn	V _{CB0} =35B; I _C =50 MA; P _D =350 MBT; h ₂₁ =300900; f _T >50 MFu	SOT23,SOD23	B·E·C
CIR	CMPT5089	CSI	npn	V _{г80} = 30 B; I _с = 50 мА; P _п = 350 мВт; h ₂₁ = 4001200; f _т > 50 МГц	SOT23,SOD23	B·E·C
CIt	BCW29	PHIL	pnp	V _{CR0} =32 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =120260; f _T >100 MFu	SOT23,SOD23	B·E·C
CIU	CMPT2484	CSI	npn	V _{G80} =60 B; I _C =50 mA; P _D =350 mBT; h ₂₁ =250800	SOT23,SOD23	B-E-C
C _{1B}	CMPT6427	CSI	npn	V _{G80} =40 B; I _C =500 мA; P _D =350 мВт; h ₂₁ =10 к100 к; f _T >130 МГц	SOT23,SOD23	B·E·C
CIX	CMPT930	CSI	non	V _{CBB} =45B; I _C =30 MA; P _D =350 MBT; h ₂₁ =100300; f _T >30 MFu	SOT23,SOD23	B-E-C
CIY	KSA1623	SAMS	non	V _{GB0} =60 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =135270; f _T >250 МГц	SOT23.SOD23	1000000000
CIZ	CMPT6517	CSI	npn	V _{DB0} =350 B; I _C =500 мА; P _D =350 мВт; h ₂₁ =20200; f _T =40200МГц	SOT23,SOD23	120000000
C2	BCW30	ALLEG	ono	V _{CB0} =30B; I _{CB0} <100 HA; h ₂₁ =215500; V _{CEIset1} <0.3B	SOT23,SOD23	1900 /A D.A
C2	BCW30	CDIL	pnp	V _{G80} =30 B; I _C =100 mA; P _D =330 mBr; h ₂₁ =215500; f _T >150 MFu	SOT23,SOD23	
02	BCW30	ZETEX	ana	V _{GR0} =30 B; I _G =100 mA; P _D =330 mBr; h ₂₁ =215500; f _T >150 MFц	SOT23,SOD23	
02	HSMS2822	HP	shd×2	V _{BB} > 15 B; V _E (I _E =30 мA) < 0.7 B; I _E (V _E =1 B) < 100 нA; C _D < 1.0 пФ	SOT23,SOD23	
C2	HSMS282C	HP	shd×2	V _{BB} >15B; V _E (I _E =30 мA)<0.7B; I _R (V _R =1 B)<100 нA; C _T <1.0 пФ; R _D =12 Ом	SOT323.SC70	
02	SST112	SIL	nFET	V _{GS} =35B; P _D =350 MBT; I _{DSS} >5 MA; R _{DS(on)} <50 OM	SOT23.SOD23	the second second second
C29	CMPTA29	CSI	non	V _{CR0} =100 B; I _C =500 MA; P _D =350 MB; i _D =500 MS; P _D =350 MB; i _C =500 MA; P _D =350 MB; i _C =500 MB; i _C	SOT23,SOD23	7,37,57
C2A	CMPT3906	CSI	pnp	V _{C80} =40 B; I _C =200 мА; Р ₀ =350 мВг; I ₂₁ =100300; f ₁ >125 мГц	SOT23,SOD23	130000 30
C2A	ZDC833A	ZETEX	var×2	V _B <25B; C _{2B} =29.733.6πΦ; C _{2B} /C _{20B} =56.5; Q>200	SOT23,SOD23	
C2D	CMPTA92	CSI	pnp	V _{CR0} =300 B; I _C =500 MA; P _D =350 MBT; h ₂₁ >25; f _T >50 MΓ _{II}	SOT23,SOD23	
22F	CMPT2907A	CSI	pnp	V _{CR0} =500 B; I _C =500 MA; P _D =350 MB1; H ₂₁ 223; I _T 250 WILU V _{CR0} =60 B; I _C =600 MA; P _D =350 MB1; H ₂₁ =100300; f _T >200 MFu	SOT23,30D23	
C2G	CMPTA56	CSI	*	000	SOT23,SOD23	
C2J	CMPT3640	CSI	pnp	V _{CBO} =80 B; I _C =500 мA; P _D =350 мBr; h ₂₁ >50; f _T >100 МГц	SOT23,SOD23	
C2L	CMPT5040	CSI	pnp	V _{CB0} =12B; I _C =80 MA; P _D =350 MBT; h ₂₁ =30120; f _T >500 MFu		TV- 0
C2o		PHIL	pnp	V _{CB0} =160 B; I _C =500 мА; Р _D =350 мВт; h ₂₁ =60240; f _T =100300 МГц	SOT23,SOD23	
	BCW30		pnp	V _{C80} =32 B; I _C =100 MA; P _D =250 MBr; h ₂₁ =215500; f _T >100 MFц	SOT23,SOD23	
C2P	CMPT5086	CSI	pnp	V _{C80} =50 B; I _C =50 MA; P _D =350 MBT; h ₂₁ =150500; f _T >40 MFL	SOT23,SOD23	
C2Q	CMPT5087	CSI	pnp	V _{C80} =50 B; I _C =50 mA; P _D =350 mBT; h ₂₁ =250800; f _T >40 MFU	SOT23,SOD23	
C2R	CMPT3646	CSI	npn	V _{C80} =40 B; I _C =200 κA; P _D =350 κBτ; h ₂₁ =30120; f _T >350 ΜΓц	SOT23,SOD23	1000000
C2t	BCW30	PHIL	pnp	V_{C80} =32B; I_C =100 MA; P_D =250 MBT; h_{21} =215500; f_T >100 MF $_L$	SOT23,SOD23	
C2T	CMPT4403	CSI	pnp	V_{C80} =40 B; I_C =600 MA; P_D =350 MBT; h_{21} =100300; f_T >200 MFU	SOT23,SOD23	
C2U	CMPTA63	CSI	pnp	V_{C80} =30 B; I_C =500 MA; P_D =350 MBT; h_{21} >10000; f_T >125 MFu	SOT23,SOD23	
C _{2B}	CMPTA64	CSI	pnp	V _{CB0} =30 B; I _C =500 мA; P _D =350 мВт; h ₂₁ > 20000; f _T > 125 МГц	SOT23,SOD23	
C2W	CMPT8599	CSI	pnp	V _{C80} =80 B; I _C =500 мA; P _D =350 мВт; h ₂₁ =100300; f _T >150 МГц	SOT23,SOD23	Salara Cara
C2X	CMPT4401	CSI	npn	V _{CB0} =60 B; I _C =600 мA; P _D =350 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	1000000000
C2Z	CMPT6520	CSI	pnp	V _{CB0} =350 B; I _C =500 мА; P _D =350 мВт; h ₂₁ =20200; f _T =40200 МГц	SOT23,SOD23	CACCIONION.
C3	1PS302	PHIL	fd×2	V_R < 80 B; I_F < 200 mA; V_F (I_F = 50 mA) < 1.0 B; C_D < 1.5 n Φ ; t_{RR} < 4 HC	SOT323,SC70	
C3	1SS226	TOSH	di×2	V _R <80 B; I _F <100 mA; V _F (I _F =100 mA)<1.2 B; I _R <0.5 mkA; t _{RR} <4 hc	SOT346,SC59	
C3	1SS302	TOSH	di×2	V _R <80 B; I _E <100 mA; V _E (I _E =100 mA)<1.2 B; t _{RR} <4 hc	SOT323,SC70	
C3	1SS362	TOSH	di×2	V_R <80 B; I_F <80 mÅ; V_F (I_F =80 mÅ) < 1.2 B; I_R < 0.5 mkÅ; t_{RR} <4 hc	SOT416,SC75A	
C3	HSMS2823	HP	shd×2	V _{BR} >15B; V _F (I _F =30 мА)<0.7B; I _R (V _R =1 B)<100 нА; C _D <1.0 пФ	SOT23,SOD23	
C3	HSMS282E	HP	shd×2	$V_{BR} > 15B$; $V_{E}(I_{F}=30 \text{ mA}) < 0.7B$; $I_{R}(V_{R}=1B) < 100 \text{ mA}$; $C_{T} < 1.0 \text{ n}\Phi$; $R_{D}=120 \text{ m}$	SOT323,SC70	
C3	KST4126	SAMS	pnp	V _{GB0} =25 В; I _C =200 мА; Р _D =350 мВт; h ₂₁ =120360; f _T >250 МГц	SOT23,SOD23	305577 30
23	MMBZ5223BT	DIODS	dz	V ₂ (I _{ZT} =20 mA)=2.572.84 B; I _R <75 m kA	COCCOONE.	A·n.c.·K
23	SST113	SIL	nFET	V _{GS} =35B; P _D =350 MBT; I _{DSS} >2 MA; R _{DS(on)} <100 OM	SOT23,SOD23	D·S·G
238	SST5638	SIL	nFET	V _{DS} =30 B; P _D =350 mBT; I _{DSS} >50 mA; R _{DS(oit)} <30 Om	SOT23,SOD23	D·S·G
C39	SST5639	SIL	nFET	V _{DS} =30 B; P _D =350 MBT; I _{DSS} >25 MA; R _{DS(on)} <60 OM	SOT23,SOD23	D·S·G
C3A	CMPT3019	CSI	npn	V_{C80} = 120 B; I_C = 500 мА; P_D =350 мВт; h_{21} = 100300; f_T > 100 МГц	SOT23,SOD23	B·E·C
C3B	CMPT918	CSI	npn	V_{CB0} =30 B; I_C =50 mA; P_D =350 mBT; h_{21} >20; f_T >600 MFu	SOT23,SOD23	B-E-C
C3E	CMPTH10	CSI	npn	V _{DB0} *30B; P _D *350 MBT; h ₂₁ >60; f _T >650 MFu	SOT23,SOD23	B.E.C



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
C3Z	CMPTA44	CSI	npn	V_{CB0} =450 B; I_C =300 MA; P_D =350 MBT; h_{21} =50200; f_T >20 MFU	SOT23,SOD23	B·E·C
C4	BCW29R	PHIL	pnip	V _{свр} =32B; I _с =100мA; P _р =350мBт; h ₂₁ =120260; f _T >100МГц	SOT23,SOD23	B·E·C
C4	BCW29R	ZETEX	pnp	V _{CBD} =30B; I _C =100 мA; P _D =330 мВт; h ₂₁ =120260; f _T >150 МГц	SOT23,SOD23	E·B·C
C4	HSMS2824	HP	shd×2	$V_{BB} > 15B$; $V_{E}(I_{E}=30 \text{ mA}) < 0.7B$; $I_{B}(V_{B}=1B) < 100 \text{ mA}$; $C_{D} < 1.0 \text{ m}$	SOT23,SOD23	A1-A2-K1,K2
C4	HSMS282F	HP	shd×2	$V_{BR} > 15B$; $V_{E}(I_{E}=30 \text{ mA}) < 0.7B$; $I_{B}(V_{B}=1B) < 100 \text{ mA}$; $C_{T} < 1.0 \text{ n}\Phi$; $R_{D}=12 \text{ Om}$	SOT323,SC70	A1-A2-K2,K1
C40	SST5640	SIL	nFET	V _{DS} =30B; P _D =350 мВт; I _{DSS} >5 мА; R _{DS(on)} <100 Ом	SOT23,SOD23	D·S·G
C41	SST4091	SIL	nFET	V _{DS} =35B; P _D =350 мВт; I _{DSS} =30 мА; R _{DS/mb} <30 Ом	SOT23,SOD23	D·S·G
C42	SST4092	SIL	nFET	V _{DS} =35B; P _D =350 мВт; I _{DSS} =30 мА; R _{DS(on)} < 50 Ом	SOT23,SOD23	D-S-G
C43	SST4093	SIL	nFET	V _{DS} =35B; P _D =350 мВт; I _{DSS} =30 мА; R _{DS(nb)} < 80 Ом	SOT23,SOD23	D·S·G
C4A	CMPT4033	CSI	pnp	V _{CBD} =80 B; I _C =500 мА; P _D =350 мВт; h ₂₁ =100300; f _T > 100 МГц	SOT23,SOD23	B·E·C
C5	BCW30R	PHIL	pnio	V _{CBD} =20B; I _C =100 мA; P _D =350 мВт; h ₂₁ =215500; f _T >100 МГц	SOT23,SOD23	E·B·C
C5	BCW30R	ZETEX	pnp	V _{GBD} =30B; I _G =100мA; P _D =330мBт; h ₂₁ =215500; f _T >150МГц	SOT23,SOD23	B·E·C
C5	MMBA811C5	МОТ	pnp	V _{CBD} =50 B; I _C =50 mA; P _D =350 mBT; h ₂₁ =135270	SOT23,SOD23	B·E·C
C5	MMBZ5225BT	DIODS	dz	V ₂ (I ₇₇ =20 mA)=2.853.15 B; I _B <50 mkA	SOT523	A+n.c.+K
C56	SST4856	SIL	nFET	V _{DS} =40 B; P _D =350 мВт; I _{DSS} >50 мА; R _{DS(on)} <25 Ом	SOT23,SOD23	D·S·G
C57	SST4857	SIL	nFET	V _{DS} =40 B; P _D =350 MBT; I _{DSS} >20 MA; R _{DS(ob)} <40 OM	SOT23,SOD23	D·S·G
C58	SST4858	SIL	nFET	V _{DS} =40 B; P _D =350 MBT; I _{DSS} >8 MA; R _{DS(on)} <60 OM	SOT23,SOD23	D·S·G
C59	SST4859	SIL	nFET	V _{DS} =30 B; P _D =350 MBT; I _{DSS} >50 MA; R _{DS(on)} <25 OM	SOT23,SOD23	D·S·G
C5A	ZDC834A	ZETEX	var×2	V _B <25B; I _E <200 mA; I _B <0.02 mKA; C _{2B} =42.351.7 nΦ; C _{2B} /C _{20B} =5.06.5	SOT23,SOD23	A1+A2+K1,K2
C5C	CMPD7000	CSI	fid×2	I_0 =200 MA; V_{PRM} = 100 B; $V_F(I_F$ = 100 MA)=0.751.10 B; I_R <300 HA; I_{RR} <4.0 HC; C_T <1.5 πΦ	SOT23,SOD23	
C5D	CMPD914	CSI	fid	I _E =250 mA; V _B =75 B; V _E (I _E =10 mA) < 1.0 B; I _B < 25 πA; t _{BB} < 4.0 πC; C _T < 4.0 πΦ	SOT23,SOD23	A•n.c.•K
C6	MMBA811C6	SAMS	pnp	V _{CB0} =50 B; I _C =50 mA; P _D =350 mBT; h ₂₁ =200400	SOT23,SOD23	B·E·C
C6	MMBA811C6	МОТ	pnp	V _{CBD} =50 B; I _C =50 mA; P _D =300 mBT; h ₂₁ =200400	SOT23,SOD23	B·E·C
C60	SST4860	SIL	nFET	V _{DS} =30 B; P _D =350 мВт; I _{DSS} >20 мА; R _{DS(qq)} <40 Ом	SOT23,SOD23	D·S·G
C61	SST4861	SIL	nFET	V _{DS} =30B; P _D =350 MBT; I _{DSS} >8 MA; R _{DS(m)} <60 OM	SOT23,SOD23	D·S·G
C7	MMBA811C7	SAMS	pnp	V _{CB0} =50 B; I _C =50 mA; P _D =350 mBT; h ₂₁ =300600	SOT23,SOD23	B·E·C
C7	MMBA811C7	MOT	pnp	V _{CR0} =50 B; I _C =50 мА; P _D =300 мВт; h ₂₁ =300600	SOT23,SOD23	B·E·C
C77	BCF29R	PHIL	pnp	V _{CBD} =32B; I _C =100 мА, P _D =350 мВт; h ₂₁ =120260; f _T >100 МГц	SOT23,SOD23	E·B·C
C7H	CMPT5179	CSI	non	V _{CBD} =20B; I _C =50 мA; P _D =350 мВт; h ₂₁ >25; f _T >900 МГц	SOT23,SOD23	B·E·C
С7р	BCF29	PHIL	pnp	V _{CB0} =32B; I _C =100 мA; P _D =250 мВт; h ₂₁ =120260; f _T >100МГц	SOT23,SOD23	B·E·C
C8	BCF30	SGS	pnp	V _{CBD} =32B; I _C =100 мA; P _D =250 мВт; h ₂₁ =215500; f _T >100МГц	SOT23,SOD23	B·E·C
C8	MMBA811C8	SAMS	pnp	V _{CB0} =50 B; I _C =50 mA; P _D =350 mBT; h ₂₁ =450900	SOT23,SOD23	B·E·C
C8	MMBA811C8	МОТ	pnp	V _{сво} =50 B; I _c =50 мA; P _D =300 мВт; h ₂₁ =450900	SOT23,SOD23	B·E·C
C8A	CMPZ5226B	CSI	dz	V _x (I _{zz} =20 mA)=3.1353.465B; I _z (V _B =1.0 B)<25 mkA; Z _{zz} (I _{zz} =20 mA)<28 0 m	SOT23,SOD23	A+n.c.+K
C8B	CMPZ5227B	CSI	dz	V _x (I _{zz} =20 mA)=3.423.78 B; I ₁ (V _B =1.0 B)<15 m; A; Z _{zz} (I _{zz} =20 mA)<24 Om	SOT23,SOD23	A+n.c.+K
C8C	CMPZ5228B	CSI	dz	V ₄ (I ₇₇ =20 MA)=3.7054.095B; I ₁ (V ₀ =1.0 B)<10 MKA; Z ₇₇ (I ₇₇ =20 MA)<23 DM	SOT23,SOD23	A·n.c.·K
C8D	CMPZ5229B	CSI	dz	V _x (₂₇ =20 mA)=4.0854.515B; l _c (V _B =1.0 B)<5.0 mrA; Z _x (₁ V ₂ =20 mA)<220 m	SOT23,SOD23	A•n.c.•K
C8E	CMPZ5230B	CSI	dz	$V_{x}l_{zz}^{-2}$ 20 mA)=4.4654.935B; $I_{L}(V_{n}$ =2.0B}<5.0 mrA; $Z_{z}^{-1}l_{zz}^{-1}$ 20 mA)<190 m	SOT23,SOD23	A•n.c.•K
C8F	CMPZ5231B	CSI	dz	$V_X I_{ZT}^{+20} MA$)=4.8455.355B; $I_L (V_P = 2.0 B) \le 5.0 \text{ m/A}$; $Z_{ZT} I_{ZT}^{-20} MA$) $\le 17.0 \text{ m}$	SOT23,SOD23	A+n.c.+K
C8G	CMPZ5232B	CSI	dz	$V_Z(I_{ZT}^{-2}0 \text{ mA}) = 5.3205.880 \text{ B}; I_L(V_B^{-2}3.0 \text{ B}) \le 5.0 \text{ m/A}; \\ Z_{ZT}(I_{ZT}^{-2}0 \text{ mA}) \le 110 \text{ m}$	SOT23,SOD23	A•n.c.•K
C8H	CMPZ5233B	CSI	dz	V _Z (I _{ZT} =20 мA)=5.7006.300B; I _L (V _R =3.5B)<5.0 мкA; Z _{ZT} (I _{ZT} =20 мA)<7.0 0м	SOT23,SOD23	10.000000000000000000000000000000000000
C8J	CMPZ5234B	CSI	dz	$V_{\mathcal{L}}(I_{ZT}^{*}20 \text{ mA})$ = 5.8906.510 B; $I_{L}(V_{B}^{*}4.0 \text{ B})$ < 5.0 m/A; $Z_{ZT}(I_{ZT}^{*}20 \text{ mA})$ < 7.0 0 m	SOT23,SOD23	
C8K	CMPZ5235B	CSI	dz	$V_Z(I_{ZT}$ =20 mA)=6.4607.140B; $I_L(V_P$ =5.0B)<3.0 mrA; $Z_{ZT}(I_{ZT}$ =20 mA)<5.00m	SOT23,SOD23	A•n.c.•K
C8L	CMPZ5236B	CSI	dz	V _Z (I _{ZT} =20 мA)=7.1257.875B; I _L (V _R =6.0 B)≤3.0 мкA; Z _{ZT} (I _{ZT} =20 мA)≤6.0 Oм	SOT23,SOD23	A•n.c.•K

C8N C8p C8p	CMPZ5237B CMPZ5238B BCF30 CMPZ5239B CMPZ5239B CMPZ5240B CMPZ5241B CMPZ5241B CMPZ5242B CMPZ5244B CMPZ5244B	CSI CSI PHIL CSI CSI CSI CSI CSI CSI	dz dz pnp dz dz dz dz dz dz dz	$ \begin{array}{l} V_2 I_{27} = 20 \text{mA}) = 7.790 \dots 8.810 B_1 I_2 V_{R} = 6.5 B) < 3.0 \text{m/A}; \\ Z_{17} I_{27} = 20 \text{mA}) < 6.00 \text{m} \\ V_2 I_{17} = 20 \text{mA}) = 8.265 \dots 9.135 B_1 I_2 V_{R} = 6.5 B) < 3.0 \text{m/A}; \\ Z_{17} I_{27} = 20 \text{mA}) < 8.00 \text{m} \\ V_{280} = 328 I_{17} = 100 \text{mA}; P_{17} = 250 \text{mB}; h_{21} = 215 \dots 500, f_{17} > 100 \text{m} \text{fu} \\ V_2 I_{17} = 20 \text{mA}) = 8.645 \dots 9.555 B_1 I_2 V_{R} = 6.5 B) < 3.0 \text{m/A}; \\ Z_{17} I_{17} = 20 \text{mA}) < 50.0 \text{m} \text{fu} \\ V_2 I_{17} = 20 \text{mA}) < 9.500 \dots 10.55 B_1 I_2 V_{R} = 8.0 B) < 3.0 \text{m/A}; \\ Z_{17} I_{17} = 20 \text{mA}) < 10.45 \dots 11.55 B_1 I_2 V_{18} = 8.4 B) < 2.0 \text{m/A}; \\ Z_{17} I_{17} = 20 \text{mA}) < 10.45 \dots 11.55 B_1 I_2 V_{R} = 9.8 B) < 3.0 \text{m/A}; \\ Z_{17} I_{17} = 20 \text{mA}] < 14.0 \dots 14.0 B_1 I_2 V_{R} = 9.8 B) < 3.0 \text{m/A}; \\ Z_{17} I_{17} = 20 \text{mA}] < 13.00 \text{m} \\ V_2 I_{17} = 20 \text{mA}] < 13.00 \text{m} \\ V_3 I_{17} = 20 \text{mA}] < 13.00 \text{m} \\ V_4 I_{17} = 20 \text{mA}] < 13.00 \text{m} \\ V_4 I_{17} = 3.5 \text{mA}] < 12.5 \dots 13.65 B_1 I_2 V_{17} = 9.8 B) < 0.5 \text{m/A}; \\ Z_{17} I_{17} I_{17} = 10.35 \text{m} \text{m} \text{m} \\ V_{17} I_{17} = 3.5 \text{m} $	Kopnyc SOT23,SOD23 SOT23,SOD23 SOT23,SOD23 SOT23,SOD23 SOT23,SOD23 SOT23,SOD23 SOT23,SOD23 SOT23,SOD23	ArnerK Brec ArnerK ArnerK ArnerK
C8p C8P	BCF30 CMPZ5239B CMPZ5240B CMPZ5241B CMPZ5242B CMPZ5243B CMPZ5243B CMPZ5244B 1SS307	PHIL CSI CSI CSI CSI CSI CSI	pnp dz dz dz dz dz	\forall_{eff} = 20 \text{ mA} \cdot \text{ 8.2659 135B, \forall_{eff} \cdot \text{ 5.8} \cdot \text{ 3.0 mmA}; \\ \frac{2}{2} \text{ ma} \cdot \text{ 2.0 mmA}; \\ \frac{2}{2} \text{ ma} \cdot \text{ 3.0 mmA}; \\ \frac{2}{2} \text{ 1.0 mmA}; \\ \frac{2}{2} 1.0 mmA	SOT23,SOD23 SOT23,SOD23 SOT23,SOD23 SOT23,SOD23 SOT23,SOD23	B-E-C A-n.cK A-n.cK A-n.cK
C8P C8Q C8R C8S C8T C8U C9 C9 CA CA CA CA CA CA	CMPZ5239B CMPZ5240B CMPZ5241B CMPZ5242B CMPZ5242B CMPZ5243B CMPZ5244B 1SS307	CSI CSI CSI CSI CSI CSI	dz dz dz dz dz	\forall V_1\text{Lpt}-20 \text{ in A} \text{: 8 B45 9 555 B, \text{ i, Vis = 6 5 B} \le 3.0 \text{ in KA}; \\ \frac{2}{2}\text{Lpt}-20 \text{in A} \text{: 10 0 m} \\ \frac{1}{2}\text{Lpt}-20 \text{in A} \text{: 10 0 m} \\ \frac{1}{2}\text{Lpt}-20 \text{in A} \text{: 10 0 m} \\ \frac{1}{2}\text{Lpt}-20 \text{in A} \text{: 17 0 m} \\ \frac{1}{2}\text{Lpt}-20 \text{in A} \text{: 17 0 m} \\ \frac{1}{2}\text{Lpt}-20 \text{in A} \text{: 15 B, \text{i, Vis} = 8 A B \text{ 2 0 m M A}; \\ \frac{1}{2}\text{Lpt}-20 \text{in A} \text{: 12 0 m} \\ \frac{1}{2}\text{Lpt}-20 \text{in A} \text{: 14 0 12 60 B, \text{I, Vis}-9 B \text{ 1 0 m M A}; \\ \frac{1}{2}\text{Lpt}-20 \text{M} \text{ 20 m M} \\ \frac{1}{2}\text{Lpt}-20 \text{M} \text{ 20 m M} \text{ 25 0 m M}; \\ \frac{1}{2}\text{Lpt}-25 \text{In M} \text{ 25 0 m M}; \\ \frac{1}{2}\text{Lpt}-35 \text{ in M} \text{ 25 0 m M}; \\ \frac{1}{2}\text{Lpt}-35 \text{ 25 0 m M}; \\ \frac{1}{2}\text{ 25 0 m M}; \\ \frac{1}{2} 25 0 m M	SOT23,SOD23 SOT23,SOD23 SOT23,SOD23 SOT23,SOD23	ArnerK ArnerK ArnerK
C8Q C8R C8S C8T C8U C9 C9 CA CA CA CA CA CA	CMPZ5240B CMPZ5241B CMPZ5242B CMPZ5243B CMPZ5244B 1SS307	CSI CSI CSI	dz dz dz dz	Z _e (I ₂ -; 20vA) < 1.00m V ₂ (I ₁ -; 20vA) + 9.500 10.50B, I ₄ (V _B -8.0 B) < 3.0 mrA; Z _e (I ₂ -; 20vA) + 17.0m V ₂ (I ₁ -; 20vA) + 10.45 11.55B, I ₄ (V _B -8.4 B) < 2.0 mrA; Z _e (I ₂ -; 20vA) < 22.0m V ₂ (I ₁ -; 20vA) < 3.00m Z _e (I ₂ -; 20vA) < 3.00m Z _e (I ₂ -; 20vA) < 3.00m V ₂ (I ₁ -; 20vA) < 3.00m V ₂ (I ₁ -; 20vA) < 3.00m	SOT23,SOD23 SOT23,SOD23 SOT23,SOD23	A·n.c.·K A·n.c.·K
C8R C8S C8T C8U C9 C9 CA CA CA	CMPZ5241B CMPZ5242B CMPZ5243B CMPZ5244B 1SS307	CSI CSI	dz dz dz	\(\frac{V_{eff}}{2} = 20 \text{ mA} \) \(\frac{9}{2} = 50 \text{ mA} \) \(\frac{1}{2} \text{ mA} \) \(\frac{1}{2} = 20 \text{ mA} \) \(\frac{1}{2} = 10 \text{ mA} \) \(\frac{1}{2} = 20 \text{ mA} \) \(\frac{1} = 20 \text{ mA} \) \(\frac{1}{2} = 20 \text{ mA} \) \(SOT23,SOD23 SOT23,SOD23	A·n.c.·K
C8S C8T C8U C9 C9 CA CA	CMPZ5242B CMPZ5243B CMPZ5244B 1SS307	CSI	dz dz	\[\frac{Z_{27}(Q_{27}^2 20 \times A) \leq 22 \times A \\ \frac{V_{27}}{20 \times A} \leq 20 \times A \\ \frac{V_{27}}{20 \times A} \rightarrow 11.40 \ldots \leq 0.8 \\ \leq \ldots \leq \frac{V_{27}}{20 \times A} \rightarrow 30 \times A \\ \frac{V_{27}(Q_{27}^2 20 \times A) \rightarrow 12.6 \ldots \leq \ldots	SOT23,SOD23	
C8T C8U C9 C9 CA CA CA	CMPZ5243B CMPZ5244B 1SS307	CSI	dz	Z _{Z1} (I _{Z1} =20MA)<300M V _Z (I _{Z1} =9.5MA)=12.3513.65B; I _L (V _B =9.9B)<0.5MkA;		A•n.c.•K
C8U C9 CA CA CA CA CA CA CA	CMPZ5244B 1SS307				SOT23 SOD23	
C9 C9 CA	1SS307	CSI	dz			A·n.c.·K
CA I	100000000		uZ	V _Z (I _{ZT} =9.0 mA)=13.3014.70B, I _L (V _R =10 B)<0.1 mrA; Z _{ZT} (I _{ZT} =9.0 mA)<150m	SOT23,SOD23	A·n.c.·K
CA CA	DOCTOR	TOSH	di	V _B <30 B; I _F <100 mA; V _F (I _F =100 mA)<1.3 B; I _B <0.01 mKA	SOT346,SC59	A•n.c.•K
CA	BCF30R	PHIL	pnp	V_{CB0} =32B; I_C =100 mA; P_0 =350 mBr; h_{21} =215500; f_T >100 M Γ_{IJ}	SOT23,SOD23	E·B·C
	BCW61AR	ZETEX	pnp	V _{C80} =32B; I _C =200 мA; P _D =330 мВт; h ₂₁ =120220; f _T >180 МГц	SOT23,SOD23	B-E-C
D4 .	BCW61AR	PHIL	onp	V _{сво} =32 B; I _c =200 мA; P _D =250 мВт; h ₂₁ =120220; f _T >100 МГц	SOT23,SOD23	C·B·E
CA I	MMBZ4691	VISH	dz	V ₂ (I ₂₇ =50 mKA)=5.896.51 B; I _B < 10 mKA	SOT23,SOD23	A·n.c.·K
CA I	RN1444A	TOSH	Dnpn	V _{GB0} =50 B; I _G =300 MA; P _D =200 MBT; h ₂₁ =200700; f _T =30 MFu; R ₁ =2.2 KOM	SOT346,SC59	B·E·C
CA :	SST4391	SIL	nFET	V _{DS} =40 B; P _D =350 mBT; I _{DSS} >50 mA; g _F =6 mCm; R _{DS(on)} =30 Om	SOT23,SOD23	D·S·G
CA2	CMPD2836	CSI	fid×2	I_0 =200 MA; V_{RRM} =75 B; $V_E (I_E$ =100 MA)<1.2 B; I_R <100 HA; I_{RR} <4.0 HC; C_T <4.0 M Φ	SOT23,SOD23	
CA6	CMPD2838	CSI	fid×2	₀ =200 MA; V _{PRM} =75 B; V _E (I _E =100 MA) < 1.2 B; I _R < 100 HA; t _{PR} < 4.0 HC; C _T < 4.0 nΦ	SOT23,SOD23	A2+A1+K2,K1
CAR :	2SA1885R	ROHM	pnp	V _{CEO} =15B; I _C =100 mA; h ₂₁ =180390; f _T >650 MFu	SOT416,SC75A	B·E·C
CAS :	2SA1885S	ROHM	pnp	V _{CED} =15B; I _C =100 mA; h ₂₁ =270560; f _T >650 MF _U	SOT416,SC75A	B·E·C
CB I	BCW61BR	ZETEX	pnp	V _{CB0} =32 B; I _C =200 мA; P _D =330 мВт; h ₂₁ =180310; f _T >180 МГц	SOT23,SOD23	B·E·C
CB I	BCW61BR	PHIL	pnp	V _{CB0} =32B; I _C =100 мA; P _D =330 мВт; h ₂₁ =180310; f _T =250 МГц	SOT23,SOD23	C·B·E
CB	RN1444B	TOSH	Dnpn	V _{CB0} =50 B; I _C =300 мA; P _D =200 мВт; h ₂₁ =3501200; f ₁ =30 МГц; R ₁ =2.2 кОм	SOT346,SC59	B·E·C
CB :	SST4392	SIL	nFET	V _{DS} =40 B; P _D =350 mBT; I _{DSS} >25 mA; g _F =6mc; R _{DS(en)} =60 Om	SOT23,SOD23	D·S·G
CC :	2SA1122B	REN	pnp	V _{GB0} =55B; I _G =100 MA; P _D =150 MBT; h ₂₁ =160320	SOT23,SOD23	B·E·C
CC :	2SA2081C	REN	onp	V _{CB0} =55B; I _C =100 MA; P _D =150 MBT; h ₂₁ =160320	SOT323,SC70	B-E-C
CC I	BCW61CR	ZETEX	gng	V _{cs0} =32 B; I _c =200 мA; P _D =330 мВт; h ₂₁ =250460; f _T >180 МГц	SOT23.SOD23	B·E·C
CC I	BCW61CR	PHIL	ana	V _{св0} =32 B; I _C =200 мА; P _D =330 мВт; h ₂₁ =250460; f _T >180 МГц	SOT23.SOD23	C·B·E
CC I	BF554	SIEM	non	V _{CB0} =20B; I _C =30mA; P _D =280 mBT; h ₂₁ =60250; f _T >250 MFu	SOT23.SOD23	B·E·C
	SST4393	SIL	nFET	V _{DS} =40 B; P _D =350 mB+; I _{DSS} >5 mA; g _E =6mc; R _{DSkml} =100 0m	SOT23.SOD23	D·S·G
cc :	ZMDC831B	ZETEX	var×2	$V_R < 25B$; $I_F < 200 \text{ mA}$; $I_R < 0.02 \text{ mrA}$; $C_{2B} = 14.2515.75 \text{ n}\Phi$; $C_{2B}/C_{200} = 4.56$	SOT323,SC70	A1+A2+K1,K2
CC10	CMPZDC27V	CSI	dz×2	V ₂ =27B(5%); P _D <350 MBT	SOT23.SOD23	A1+A2+K1.K2
CC11	CMPZDC30V	CSI	dz×2	V ₂ =30B(5%); P _D <350mBt	SOT23,SOD23	A1-A2-K1,K2
CC12	CMPZDC33V	CSI	dz×2	V ₂ =33B(5%); P _D <350 MBT	SOT23,SOD23	
	CMPZDC36V	CSI	dz×2	V ₂ =36B(5%); P ₀ <350 MBr	SOT23,SOD23	
	CMPZDC39V	CSI	dz×2	V ₇ =39B(5%); P ₀ <350mBr	SOT23,SOD23	
	CMPZDC43V	CSI	dz×2	V ₂ =43B(5%); P _D < 350 MBT	SOT23,SOD23	
	CMPZDC47V	CSI	dz×2	V ₂ =47B(5%); P ₀ <350mBr	SOT23,SOD23	
	CMPZDC2V4	CSI	dz×2	V ₂ =2.4B(5%); P _D <350 MBT	SOT23,SOD23	
	CMPZDC2V7	CSI	dz×2	V ₂ =2.7B(5%); P ₀ <350MBT	SOT23,SOD23	
	CMPZDC3V0	CSI	dz×2	V ₂ =3.0B(5%); P ₀ <350MBT	SOT23,SOD23	-
	CMPZDC3V3	CSI	dz×2	V ₂ =3.3B(5%); P ₀ <350 MBT	SOT23,SOD23	The second second second
	CMPZDC3V3	CSI	dz×2	V ₂ =3.5 B(5%); P _D <350 MBT	SOT23,SOD23	
	CMPZDC3V6 CMPZDC3V9	CSI	dz×2	V _Z =3.0 B(5%); P _D <350 MBT V _Z =3.9 B(5%); P _D <350 MBT	SOT23,SOD23	





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
CCW9	CMPZDC4V3	CSI	dz×2	Vz=4.3B(5%); Pg<350MBt	SOT23,SOD23	A1-A2-K1,K2
CCY1	CMPZDC11V	CSI	dz×2	Vz=11 B(5%); Pn < 350 MBT	SOT23,SOD23	A1-A2-K1,K2
CCY2	CMPZDC12V	CSI	dz×2	V _Z =12 B(5%); P _D <350 MBr	SOT23,SOD23	A1 · A2 · K1, K2
CCY3	CMPZDC13V	CSI	dz×2	V ₂ =13 B(5%); P ₀ < 350 MBT	SOT23,SOD23	A1-A2-K1,K2
CCY4	CMPZDC15V	CSI	dz×2	V _z =15 B(5%); P _D <350 мВт	SOT23,SOD23	A1-A2-K1,K2
CCY5	CMPZDC16V	CSI	dz×2	V _z =16 B(5%); P _D <350 MBT	SOT23,SOD23	A1-A2-K1,K2
CCY6	CMPZDC18V	CSI	dz×2	V ₂ =18 B(5%); P _D <350 MBr	SOT23,SOD23	A1-A2-K1,K2
CCY7	CMPZDC20V	CSI	dz×2	V ₇ =20 B(5%); P ₀ < 350 MBT	SOT23,SOD23	A1-A2-K1,K2
_	CMPZDC22V	CSI	dz×2	V _z =22 B(5%); P _D <350 MB _T	SOT23,SOD23	
	CMPZDC24V	CSI	dz×2	V ₂ =24 B(5%); P ₀ <350 MBr	SOT23.SOD23	
	CMPZDC4V7	CSI	dz×2	V2=4.7B(5%); Pn <350 mBr	SOT23,SOD23	
	CMPZDC5V1	CSI	dz×2	V _z =5.1B(5%); P _D <350 MBT	SOT23.SOD23	
	CMPZDC5V6	CSI	dz×2	V _z =5.6B(5%); P _D <350 mBr	SOT23,SOD23	
	CMPZDC6V2	CSI	dz×2	V _Z =6.2B(5%); P _D <350 MBr	SOT23.SOD23	
_	CMPZDC6V8	CSI	dz×2	V ₇ =6.8B(5%); P ₀ <350 MBT	SOT23,SOD23	
	CMPZDC7V5	CSI	dz×2	V _Z =7.5B(5%); P _D <350MBT	SOT23,SOD23	
	CMPZDC7V3	CSI	dz×2	V _Z =8.2B(5%); P _D <350MB1	SOT23,SOD23	
		CSI	dz×2			
200	CMPZDC9V1 CMPZDC10V	CSI	dz×2	V _Z =9.1 B(5%); P ₀ <350 MBT V _Z =10 B(5%); P ₀ <350 MBT	SOT23,SOD23 SOT23,SOD23	
CD	2SA1122C	REN		CALL COLOR OF THE CALL COLOR C	SOT23,SOD23	
	100.00.0.0000000		pnp	V _{CB0} =55B; I _C =100mA; P _D =150mBr; h ₂₁ =250500		122.52 10
CD	2SA2081D	REN	pnp	V _{CB0} =55B; I _C =100mA; P _D =150mBr; h ₂₁ =250500	SOT323,SC70	
CD	BCW61DR	ZETEX	pnp	V _{CB0} =32B; I _C =200мA; P _D =330мBт; h ₂₁ =380630; f _T >180МГц	SOT23,SOD23	
CD	BCW61DR	PHIL	pnp	V _{CB0} -32B; I _C =200мA; P _D =330мBт; h ₂₁ =380630; f _T >180МГц	SOT23,SOD23	
CD	ZMDC832B	ZETEX	var×2	$V_R < 25B$; $I_F < 200$ mA; $I_R < 0.02$ mrA; $C_{2B} = 20.923.1$ n Φ ; $C_{2B}/C_{20.8} = 56.5$	SOT323,SC70	
CDs	BSS81B	SIEM	npn	V _{CB0} =75B; I _C =800мA; P _D =330мBт; h ₂₁ =40120; f _T =250МГц	SOT23,SOD23	
CE	2SA1122D	REN	pnp	V _{CB0} =55B; I _C =100 MA; P _D =150 MBT; h ₂₁ =400800	SOT23,SOD23	T017171
CE	BSS79B	ZETEX	npn	V _{CB0} =75B; I _C =800мA; P _D =330мBт; h ₂₁ =40120; f _T >250МГц	SOT23,SOD23	
CEs	BSS79B	SIEM	npn	V _{CB0} =75B; I _C =800мA; P _D =330мBт; h ₂₁ =40120; f _T =250МГц	SOT23,SOD23	
CF	BSS79C	ZETEX	npn	V _{CB0} =75 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	
CF	MMBZ4681	VISH	dz	V _Z (I _{ZT} =50 mkA)=2.282.52 B; I _R < 2 mkA	SOT23,SOD23	
CFs	BSS79C	SIEM	npn	V_{CB0} =75B; I_C =800mA; P_D =330mBT; h_{21} =100300; f_T =250MF μ	SOT23,SOD23	100000000000000000000000000000000000000
CG	2SA1587G	TOSH	pnp	V_{CB0} =120 B; I_C =100 MA; P_D =100 MBT; h_{21} >200400; f_T >=100 MFu	SOT323,SC70	
CG	BCX71GR	ZETEX	pnp	V _{CB0} =45 B; I _C =200 мA; P _D =330 мВт; h ₂₁ =120220; f _T >180 МГц	SOT23,SOD23	B·E·C
CG	BCX71GR	PHIL	pnp	V_{CB0} =45 B; I_{C} =200 mA; P_{D} =250 mBr; h_{21} =120220; f_{T} >100 M Γ_{II}	SOT23,SOD23	C-B-E
CG	BRA124ECM	REN	Dpnp	V _{CC} =50 B; I _{OUT} =100 mA; P _D =150 mBT; h ₂₁ >56; 22 к/22 к	SOT323,SC70	B·E·C
CG	BRA124EMP	REN	Dpnp	V _{CC} =50 B; I _{OUT} =100 mA; P _D =150 mBr; h ₂₁ >56; 22 к/22 к	SOT23,SOD23	B·E·C
CGs	BSS81C	SIEM	npn	V _{CB0} =75 B; I _C =800 мА; P _D =330 мВт; h ₂₁ =100300; f _T =250 МГц	SOT23,SOD23	B·E·C
CH	1SS351	SANYO	shd×2	V _R >5B; V _F (I _F =1 mA)<0.23B; I _F (V _R =0.5B)<25 mKA	SOT23,SOD23	A1 · K2 · K1, A2
CH	BSS80B	ZETEX	pnp	V _{CB0} =60 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =40120; f _T >200 МГц	SOT23,SOD23	B·E·C
CH	BSS82BL	MOT	pnp	V _{CB0} =60 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =40120; f _T >200 МГц	SOT23,SOD23	B·E·C
CH	MMBZ4682	VISH	dz	V _Z (I _{ZT} =50 mKA)=2.572.84B; I _B <1 mKA	SOT23,SOD23	A+n.c.+K
CHA	2SC4667A	TOSH	npn	V _{CB0} =15B; I _C =200 мA; P _D =100 мВт; h ₂₁ >6001800; f _T >250 МГц	SOT323,SC70	B·E·C
CHB	2SC4667B	TOSH	npn	V _{GB0} =15B; I _G =200 мА; P _D =100 мВт; h ₂₁ > 12003600; f _T > 250 МГц	SOT323,SC70	B·E·C
CHs	BSS80B	SIEM	pnp	V _{CB0} =60 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =40120; f _T =250 МГц	SOT23,SOD23	B·E·C
CJ	BSS80C	ZETEX	pnp	V _{CB0} =60 B; I _C =800 мА; P _D =330 мВт; h ₂₁ =100300; f _T >200 МГц	SOT23,SOD23	B·E·C
CJ	MMBZ4683	VISH	dz	V _X (I _{ZZ} =50 mKA)=2.853.15 B; I _B <0.8 mKA	SOT23,SOD23	10.7/20
CJs	BSS80C	SIEM	ono	V _{CBD} =60B; I _C =800мA; P _D =330мBт; h _{Ot} =100300; f _T =250МГц	SOT23.SOD23	NOT ASSESSED ASSESSED.
CK	BCX71JR	PHIL	onp	V _{CR0} =45B; I _C =200 MA; P _D =250 MBT; h ₂₁ =250460; f _T >100 MFu	SOT23,SOD23	
CK	BCX71KR	ZETEX	pnp	V _{CBD} =45 B; I _C =200 MA; P _D =330 MBT; h ₂₁ =380630; f _T >180 MFц	SOT23,SOD23	
CK	MMBZ4684	VISH	dz	V _Z (I _{ZI} =50 mkA)=3.143.47 B ₁ I _R <7.5 mkA	SOT23,SOD23	
	CMPT8099	CSI	non	V _{CBB} =80 B; I _C =500 mA; P _D =350 mBr; h ₂₁ =100300; f _T >150 MFu	SOT23,SOD23	Committee of the commit
CKB						

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
CL	BSS82B	ZETEX	pnp	V _{G80} =60 B; I _C =800 мА; P _D =330 мВт; h ₂₁ =40120; f _T >200 МГц	SOT23,SOD23	B·E·C
CLs	BSS82B	SIEM	gng	V _{CB0} =60 B; I _C =800 мА; P _D =330 мВт; h ₂₁ =40120; f _T =250 МГц	SOT23,SOD23	B·E·C
CM	BSS82C	ZETEX	pnp	V ₀₈₀ =60 B; I _C =800 мА; P _D =330 мВт; h ₂₁ =100300; f _T >200 МГц	SOT23,SOD23	B·E·C
CM	MMBZ4685	VISH	dz	V ₂ (I ₂₇ =50 mKA)=3.423.78 B; I _B <7.5 mKA	SOT23,SOD23	A•n.c.•K
CMs	BSS82C	SIEM	pnp	V _{сво} =60 B; I _с =800 мА; P _о =330 мВт; h ₂₁ =100300; f ₁ =250 МГц	SOT23,SOD23	
CN	2SK3348	REN	nMOS	V _{DS} =20 B; I _D =100 mA; P _D =300 mBT; R _{DS(m1)} <3.2 Om	SOT323,SC70	G·S·D
CN	MMBZ4686	VISH	dz	V ₂ (I ₂₇ =50 mKA)=3.714.10 B; I _B <5 mKA	SOT23,SOD23	A·n.c.·K
CP	2SC2411KP	ROHM	npn	V _{G80} =40 B; I _G =500 мА; P _D =200 мВт; h ₂₁ =82180; f _T >250 МГц	SOT346,SC59	B·E·C
CP	2SC4097P	ROHM	npn	V _{C80} =40 B; I _C =500 мА; P _D =200 мВт; h ₂₁ =82180; f _T >250 МГц	SOT323,SC70	B·E·C
CP	2SJ586	REN	pMOS	V _{DS} =20 B; I _D =100 мА; P _D =400 мВт; R _{DS(m)} <8.5 Ом	SOT323,SC70	G·S·D
CP	MMBZ4687	VISH	dz	V ₂ (I _{ZT} =50 mKA)=4.094.52 B; I _B <4 mKA	SOT23,SOD23	A•n.c.•K
CQ	2PB1219Q	PHIL	pnp	V _{C80} =30 B; I _C =500 мA; P _D =200 мВт; h ₂₁ =85170; f _T >100 МГц	SOT323,SC70	B·E·C
CQ	2SC2411KQ	ROHM	npn	V _{CB0} =40 B; I _C =500 мA; P _D =200 мВт; h ₂₁ =120270; f _T >250 МГц	SOT346,SC59	B-E-C
CQ	2SC4097Q	ROHM	npn	V ₀₈₀ =40B; I _C =500 мA; P _D =200 мВт; h ₂₁ =120270; f _T >250 МГц	SOT323,SC70	
CQ	MSD710Q	MOT	pnp	V _{CRO} =25B; I _C =150 MA	SOT346,SC59	B-E-C
CR	2PB1219R	PHIL	pnp	V _{G80} =30 B; I _C =500 мА; P _D =200 мВт; h ₂₁ =120240; f _T >120 МГц	SOT323,SC70	
CR	2SC2411KR	ROHM	npn	V _{CB0} =40 B; I _C =500 мA; P _D =200 мВт; h _{P1} =180390; f _T >250 МГц	SOT346,SC59	
CR	2SC4097R	ROHM	npn	V _{CB0} =40 B; I _C =500 mA; P ₀ =200 mBt; h ₂₁ =180390; f _T >250 MFu	SOT323.SC70	
CR	BCW60A	ZETEX	non	V ₀₈₀ =32B; I _C =200 мА; P _D =330 мВт; h ₂₁ =120220; f _T >250 МГц	SOT23,SOD23	B-E-C
CR	MSD701R	MOT	ono	V _{CB0} =25B; I _C =150 MA	SOT346.SC59	1102 12 130
CS	2PB1219S	PHIL	pnp	V _{C80} =30 B; I _C =500 мA; P _D =200 мВт; h ₂₁ =170340; f _T >140 МГц	SOT323,SC70	13232 32
CT	MMBZ4688	VISH	dz	V ₂ (I _{2T} =50 mkA)=4.474.94 B; I _B < 10 mkA	SOT23.SOD23	
CU	MMBZ4689	VISH	dz	V ₂ (I _{2T} =50 mKA)=4.855.36 B; I _B ≤ 10 mKA	SOT23,SOD23	
CV	1SV234		pin×2	V _R >50 B; I _E <50 mA; V _E (I _E =50 mA)=0.95 B; I _R <0.1 mkA	SOT23,SOD23	
CV	1SV246	SANYO	pin×2	V _B >50 B; I _E <50 mA; V _E (I _E =50 mA)=0.95 B; I _B <0.1 mKA	SOT323,SC70	
CV	MMBZ4690	VISH	dz	V ₂ (I _{2T} =50 MKA)=5.325.88 B; I _B < 10 MKA	SOT23.SOD23	
	MAX809LUR	MAX	mrc	V _{TB} =4.00B; V _{DD} =1.25.5B; I _{CC} <100 mKA	SOT23,SOD23	
CX	MMBZ4692	VISH	dz	V ₂ (I ₂₇ =50 mKA)=6.467.14 B; I _B < 10 mKA	SOT23,SOD23	
CY	MMBZ4693	VISH	dz	V ₂ (I _{2T} =50 mrA)=7.137.88 B; I _B ≤ 10 mrA	SOT23,SOD23	
CZ	MMBZ4694	VISH	dz	V ₂ (I _{2T} =50 mKA)=7.798.61 B; I _B ≤ 1 mKA	SOT23,SOD23	
D	IRLML5103	IR.		HEXFET; V _{DS} =30 B; I _D =0.61 A; P _D =540 MBT; P _{DS(on)} < 1 OM	SOT23,SOD23	
D	MRF577T1	MOT	ngn	V ₀₈₀ =20B; I _C =80мA; P _D =232 мВт; h ₂₁ =50300; f _T =7000МГц	SOT323,SC70	200 27 2 20
D0	HSMP3800	HP	pin	I _F <1A; V _{RR} >100B; R _S <2.0 Om; C _D <0.37 nΦ; R _H >1000 Om; R _I <8 Om	SOT23,SOD23	1000072 000
D1	AZ23B2V7	VISH	dz×2	V ₇ =2.652.75 B; R ₇ (J ₇ =5 mA) < 83 Om	SOT23,SOD23	
DI	AZ23C2V7	VISH	dz×2	V _z =2.52.9B; R _z (I _z =5 mA) < 83 Om	SOT23,SOD23	
D1	AZ23C2V7	TSC	dz×2	V _z =2.52.9B; R _z (I _z =5 мA) < 83 Ом	SOT23,SOD23	
D1	BCW31	ALLEG	npn	V _{C80} =30B; I _{C80} <100 HA; h ₂₁ =110220; V _{CEIssti} <0.25B	SOT23,SOD23	
D1	BCW31	CDIL	npn	V _{CB0} =32B; I _C =100 mA; P _D =330 mBr; h ₂₁ =110220; f _T >300 MFu	SOT23,SOD23	10/10/00/170
D1	BCW31	SAMS	npn	V _{C80} =32B; I _C =100 MA; P _D =350 MBr; h _{Pl} =110220, η 2500 MFI; V _{C80} =30B; I _C =100 MA; P _D =350 MBr; h _{Pl} =110220	SOT23,SOD23	1800000000
D1	BCW31	ZETEX	npn	V _{C80} =32B; I _C =100 MA; P _D =330 MB1; h ₂₁ =110220; f _T >300 MFu	SOT23,SOD23	
DI	HSMP3801	HP	pin	I _E <1 A; V _{RB} >100 B; R _S <2.0 Om; C _D <0.37 πΦ; R _H >1000 Om; R _I <8 Om	SOT23,SOD23	
D10	AZ23B6V2	VISH	dz×2	V ₇ =6.086.32 B; R ₇ (J ₇ =5 mA)<10 Om	SOT23,SOD23	
D10	AZ23C6V2	VISH	dz×2	V ₂ =5.86.6B; R ₂ (I ₂ =5 MA) < 10 OM	SOT23,SOD23	
D10	AZ23C6V2	TSC	dz×2	V _z =5.86.6B; R _z (J _z =5MA) < 10 OM	SOT23,SOD23	
D11	AZ23B6V8	VISH	dz×2	V ₂ =6.666.94 B; R ₂ (I ₂ =5 mA) < 8 Om	SOT23,SOD23	AND DESIGNATION OF THE PARTY OF
D11	AZ23C6V8	VISH	dz×2	V _Z =6.47.2B; R _Z (I _Z =5 MA) < 8 O M	SOT23,SOD23	
D11	AZ23C6V8	TSC	dz×2	V ₂ =6.47.2B; R ₂ (l ₂ =5 MA) < 8 OM	SOT23,30D23	
D12	AZ23B7V5	VISH	dz×2	V ₂ =7.357.65 B; R ₂ (I ₂ =5 mA) < 7 Om	SOT23,SOD23	-
D12	AZ23C7V5	VISH	dz×2	V ₂ =7.07.9B; R ₂ (I ₂ =5 MA) < 70M	SOT23,SOD23	
D12	AZ23C7V5	TSC	dz×2	V ₂ =7.07.9B; B ₂ (I ₂ =5mA)<7.0m	SOT23,SOD23	
	MECOU! VO	1,000				
D13	AZ23B8V2	VISH	dz×2	V ₂ =8.048.36 B; R ₂ (I ₂ =5 mA)<7 Om	SOT23,SOD23	





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
D13	AZ23C8V2	TSC	dz×2	Vz=7.78.7B; Rz(Iz=5mA)<70m	S0T23,S0D23	K1 · K2 · A1,A2
014	AZ23B9V1	VISH	dz×2	V ₂ =8.929.28 B; R ₂ (I ₂ =5 mA)<10 Om	SOT23,SOD23	K1 · K2 · A1 A2
D14	AZ23C9V1	VISH	dz×2	V ₂ =8.59.6B; R ₂ (I ₂ =5mA) < 100m	SOT23,SOD23	K1 · K2 · A1 , A2
D14	AZ23C9V1	TSC	dz×2	V ₂ =8.59.6B; R ₂ (I ₂ =5mA) < 100m	SOT23,SOD23	
D15	AZ23B10	VISH	dz×2	V ₂ =9.810.2B; R ₂ (I ₂ =5 mA)<150m	SOT23,SOD23	
D15	AZ23C10	VISH	dz×2	V ₂ =9.410.6 B; R ₂ (I ₂ =5 mA) < 15 Om	SOT23,SOD23	1000
D15	AZ23C10	TSC	dz×2	V ₂ =9.410.6 B; R ₂ (I ₂ =5 mA)<150m	SOT23,SOD23	
D16	AZ23B11	VISH	dz×2	Vz=10.811.2 B; Rz(Iz=5 mA)<20 Om	SOT23.SOD23	
D16	AZ23C11	VISH	dz×2	Vz=10.411.6 B; Rz(Iz=5 mA) < 20 Om	S0T23.S0D23	
D16	AZ23C11	TSC	dz×2	V ₂ =10.411.6 B, R ₂ (I ₂ =5 MA)<200M	SOT23,SOD23	
D17	AZ23B12	VISH	dz×2	V ₂ =11.812.2 B; R ₂ (I ₂ =5 MA)<20 OM	SOT23,SOD23	-
D17	AZ23C12	VISH	dz×2	V ₂ =11.412.7 B; R ₂ (₂ =5 MA)<200M	SOT23,SOD23	
D17	AZ23C12	TSC	dz×2	V ₂ =11.412.7 B; R ₂ (I ₂ =5 mA) < 20 Om	SOT23,SOD23	
D18	AZ23B13	VISH	dz×2	V ₂ =12.713.3 B; R ₂ (I ₂ =5 mA) < 25 Om	SOT23,SOD23	
D18	AZ23C13	VISH	dz×2		SOT23,SOD23	
D18	AZ23C13	TSC	dz×2	V ₂ =12.414.1 B; R ₂ (I ₂ =5mA)<250m	SOT23,SOD23	
D19	AZ23C13 AZ23B15	VISH	dz×2	V ₂ =12.414.1 B; R _Z (J ₂ =5 MA)<25 OM	SOT23,SOD23	
			-	V _z =14.715.3 B; R _Z (I _z =5 MA)<30 OM		
D19	AZ23C15	VISH	dz×2	Vz=13.815.6 B; R _Z (Iz=5 MA) < 30 OM	SOT23,SOD23	
D19	AZ23C15	TSC	dz×2	Vz=13.815.6 B; Rz(Iz=5 мA)<30 OM	SOT23,SOD23	
DIG	KSA812	SAMS	pnp	V _{CB0} =60 B; I _C =100 мA; P _D =150 мBт; h ₂₁ =200400; f _T >180 МГц	SOT23,SOD23	182.80 (2)
D1L	KSA812	SAMS	pnp	V _{CB0} =60 B; I _C =100 мA; P _D =150 мBт; h ₂₁ =300600; f _T >180 МГц	SOT23,SOD23	
D10	KSA812	SAMS	pnp	V_{CB0} =60 B; I_C =100 mA; P_D =150 mBT; h_{21} =90180; f_T >180 M Γ_{LL}	SOT23,SOD23	
D1p	BCW31	PHIL	npn	V _{CB0} =32B; I _C =100мA; P _D =250мBт; h ₂₁ =110220; f _T >100МГц	SOT23,SOD23	
D1t	BCW31	PHIL	non	V _{CB0} =32B; I _C =100 мA; P _D =250 мВт; h ₂₁ =110220; f _T >100 МГц	SOT23,SOD23	1-50/100/10
D1Y	KSA812	SAMS	pnp	V _{CB0} =60 B; I _C =100 мA; P _D =150 мBт; h ₂₁ =135270; f _T >180 МГц	SOT23,SOD23	
D2	AZ23B3V0	VISH	dz×2	Vz=2.943.06 B; Rz(Iz=5 mA)<95 Om	SOT23,SOD23	
D2	AZ23C3V0	VISH	dz×2	Vz=2.83.2B; Rz(Iz=5mA)<950m	SOT23,SOD23	
D2	AZ23C3V0	TSC	dz×2	V _Z =2.83.2B; R _Z (I _Z =5mA) < 95 Om	SOT23,SOD23	K1+K2+A1,A2
D2	BCW32	ALLEG	npn	V _{CB0} =30B; I _{CB0} <100 HA; h ₂₁ =200450; V _{CE(sat)} <0.25B	SOT23,SOD23	B·E·C
D2	BCW32	CDIL	npn	V_{CB0} =32B; I_C =100 mA; P_D =330 mBT; h_{21} =200450; f_T >300 M Γ_{IJ}	SOT23,SOD23	B·E·C
D2	BCW32	ZETEX	npn	V_{CB0} =32B; I_C =100mA; P_D =330mBt; h_{21} =200450; f_T >300M Γ_{II}	SOT23,SOD23	B·E·C
D2	HSMP3802	HP	pin×2	$I_{\rm F}$ < 1 A; $V_{\rm BR}$ > 100 B; $R_{\rm S}$ < 2.0 Om; $C_{\rm D}$ < 0.37 $\pi\Phi$; $R_{\rm H}$ > 1000 Om; $R_{\rm L}$ < 8 Om	SOT23,SOD23	A1+K2+K1,A2
D20	AZ23B16	VISH	dz×2	Vz=15.716.3 B; Rz(Iz=5 mA)<40 Om	SOT23,SOD23	K1-K2-A1,A2
D20	AZ23C16	VISH	dz×2	Vz=15.317.1 B; R _z (Iz=5 mA) < 40 Om	SOT23,SOD23	K1 · K2 · A1,A2
D20	AZ23C16	TSC	dz×2	Vz=15.317.1 B; Rz(Iz=5 mA) < 40 Om	SOT23,SOD23	K1 · K2 · A1, A2
D21	AZ23B18	VISH	dz×2	Vz=17.618.4 B; Rz(Iz=5 mA) < 50 Om	SOT23,SOD23	K1 · K2 · A1,A2
D21	AZ23C18	VISH	dz×2	Vz=16.819.1 B; Rz(lz=5 mA) < 50 Om	SOT23,SOD23	K1-K2-A1,A2
D21	AZ23C18	TSC	dz×2	Vz=16.819.1 B; Rz(lz=5 mA) < 50 Om	SOT23,SOD23	
D22	AZ23B20	VISH	dz×2	Vz=19.620.4 B; Rz(Iz=5 mA)<50 Om	SOT23,SOD23	
D22	AZ23C20	VISH	dz×2	Vz=18.821.2 B; Rz(Iz=5 mA) < 50 Om	SOT23,SOD23	
D22	AZ23C20	TSC	dz×2	Vz=18.821.2 B; Rz(Iz=5 mA)<50 Om	SOT23,SOD23	
D23	AZ23B22	VISH	dz×2	V ₂ =21.622.4 B; R ₂ (I ₂ =5 mA)<55 Om	SOT23,SOD23	
D23	AZ23C22	VISH	dz×2	V ₂ =20.823.3 B; R ₂ (I ₂ =5 mA)<550m	SOT23,SOD23	
D23	AZ23C22	TSC	dz×2	V _z =20.823.3 B; R _z (I _z =5 MA) < 55 OM	SOT23,SOD23	
D24	AZ23B24	VISH	dz×2	V _z =23.524.5 B; R _Z (_z =5 MA) < 80 OM	SOT23,SOD23	100
D24	AZ23C24	VISH	dz×2	V _z =22.825.6 B; R _z (z=5 mA) < 80 Om	SOT23,SOD23	
D24	AZ23C24	TSC	dz×2	V ₂ -22.825.6 B; R ₂ () ₂ -5 MA) < 80 OM	SOT23,50D23	
D24 D25	AZ23B27	VISH	dz×2		SOT23,SOD23	
D25	AZ23C27	VISH	-	V ₂ =26.527.5 B; R ₂ (₂ =5 MA) < 80 OM		
	12000100100100		dz×2	V _z =25.128.9 B; R _Z (I _z =5 MA)<80 OM	SOT23,SOD23	
	A700007					
D25 D26	AZ23C27 AZ23B30	TSC VISH	dz×2 dz×2	V _Z =25.128.9 B; R _Z {I _Z =5mA}<80 Om V _Z =29.430.6 B; R _Z {I _Z =5 mA}<80 Om	SOT23,SOD23 SOT23,SOD23	

Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
D26	AZ23C30	TSC	dz×2	Vz=2832B; Rz(Iz=5mA)<80 Om	SOT23,SOD23	K1-K2-A1,A2
D27	AZ23B33	VISH	dz×2	V ₂ =32.333.7 B; R ₂ (I ₂ =5 mA) < 80 Om	SOT23,SOD23	K1-K2-A1,A2
D27	AZ23C33	VISH	dz×2	V ₂ =3135B; R ₂ (I ₂ =5mA) < 80 Om	SOT23,SOD23	K1-K2-A1,A2
D27	AZ23C33	TSC	dz×2	V ₂ =3135B; R ₂ (I ₂ =5mA) <80 Om	SOT23,SOD23	K1-K2-A1,A2
D28	AZ23B36	VISH	dz×2	Vz=35.336.7 B; Rz(Iz=5 mA)<90 Om	SOT23,SOD23	K1-K2-A1,A2
D28	AZ23C36	VISH	dz×2	V ₂ =3438B; R ₂ (I ₂ =5mA) < 90 Om	SOT23,SOD23	K1-K2-A1,A2
D28	AZ23C36	TSC	dz×2	Vz=3438B; Rz(Iz=5mA)<90 Om	SOT23,SOD23	K1-K2-A1,A2
D28	BAS70W	STM	shd	V _B < 70 B; I _F < 70 mÅ; V _F (I _F = 1 mÅ) < 0.41 B; I _B < 0.1 mkÅ; C _D < 2.0 nΦ	SOT323,SC70	A·n.c.·K
D29	AZ23B39	VISH	dz×2	V ₂ =38.239.8 B; R ₂ (I ₂ =5 mA) < 90 Om	SOT23,SOD23	K1-K2-A1,A2
D29	AZ23C39	VISH	dz×2	V2=3741B; R2(I2=5mA) < 90 Om	SOT23,SOD23	K1-K2-A1,A2
D29	AZ23C39	TSC	dz×2	V2=3741B; R2(I2=5mA) < 90 Om	SOT23,SOD23	K1-K2-A1.A2
D29	BAS70-06W	STM	shd×2	V _R <70B; I _E <70 mA; V _E (I _E =1 mA)<0.41B; I _B <0.1 mrA; C _D <2.0 πΦ	SOT323.SC70	
D2p	BCW32	PHIL	npn	V _{CB0} =32 B; I _C =100 мA; P ₀ =250 мВт; h ₂₁ =200450; f _T >100 МГц	SOT23,SOD23	Control Process
D2t	BCW32	PHIL	non	V _{CB0} =32 B; I _C =100 мA; P _D =250 мВт; h _{P1} =200450; f _T >100 МГц	SOT23.SOD23	1800 /A D.A
D3	1SS187	TOSH	di	V _B <80B; I _F <100 mA; V _F (I _F =100 mA)<1.2B; I _B <0.5 mkA; t _{BB} <4 hc	SOT346,SC59	200-21 00
D3	AZ23B3V3	VISH	dz×2	V ₂ =3.233.37 B; R ₂ (I ₂ =5 mA)<95 Om	SOT23,SOD23	
D3	AZ23C3V3	VISH	dz×2	V _Z =3.13.5B; R _Z (I _Z =5mA) < 95 Om	SOT23,SOD23	
D3	AZ23C3V3	TSC	dz×2	V ₂ =3.13.5B; R ₂ (I ₂ =5 MA) < 95 OM	SOT23,SOD23	
D3	BCW33	ALLEG	non	V _{CB0} =30B; I _{CB0} <100 HA; h ₂₁ =420800; V _{CEIsall} <0.25B	SOT23,SOD23	
D3	BCW33	CDIL	npn	V _{C80} =32 B; I _C =100 мА; Р _D =250 мВт; h ₂₁ =420800; f _T >100 МГц	SOT23,SOD23	T1000 01
D3	BCW33	ZETEX	non	V _{C80} =32 B; I _C =100 MA; P _D =330 MBT; h ₂₁ =420800; f ₁ >300 MFц	SOT23,SOD23	
D30	AZ23B43	VISH	dz×2	V ₂ =42.143.9 B; R ₂ (J ₂ =5 MA)<100 Om	SOT23,30D23	
D30	AZ23C43	VISH	dz×2	V ₂ =4046B; R ₂ (I ₂ =5mA)<1000m	SOT23,SOD23	
D30	AZ23C43	DIODS	dz×2	V ₂ =4046B; R ₂ (I ₂ =5mA)<1000m	SOT23,SOD23	
D30	AZ23C43	TSC	dz×2	Vz=4046B; Rz(Iz=5mA) < 1000m	SOT23,SOD23	The Control of the Control
D30	BAS70-05W	STM	shd×2	V _B <70B; I _E <70 MA; V _E (I _E =1 MA)<0.41 B; I _B <0.1 MKA; C _B <2.0 nΦ	SOT323,30023	The second second
D31	AZ23B47	VISH	dz×2	11 11 11	SOT23,SOD23	
D31	AZ23C47	VISH	dz×2	V _Z =46.147.9 B; R _Z (I _Z =5 MA) < 100 OM		
D31	AZ23C47	DIODS	dz×2	V ₂ =4450B; R ₂ (I ₂ =5mA)<1000m	SOT23,SOD23 SOT23,SOD23	
D31	AZ23C47 AZ23C47	TSC	dz×2	V ₂ =4450B; R ₂ (I ₂ =5mA)<1000m	SOT23,SOD23	
D31	BAS70-04W	STM	shd×2	V_z =4450B; R_z (I_z =5mA)<1000m V_p <70B; I_e <70mA; V_e (I_e =1mA)<0.41B; I_e <0.1mxA; C_n <2.0πΦ	SOT323,SC70	
D31	AZ23B51	VISH	dz×2	III was a set it program to the first state of the control of the		
D32	AZ23051 AZ23C51	VISH	dz×2	Vz=5052B; Rz(Iz=5mA)<1000m	SOT23,SOD23	The state of the state of
		DIODS		Vz=4854B; Rz(Iz=5mA)<1000m	SOT23,SOD23	
D32	AZ23C51	TSC	dz×2	Vz=4854B; Rz(Iz=5mA)<1000m	SOT23,SOD23	
	AZ23C51		dz×2	Vz=4854B; Rz(Iz=5mA)<1000m	SOT23,SOD23	
D3B D3E	RB420D	ROHM	shd	V _R <40 B; I _F <100 мA; V _F (I _F =10 мA)<450 мB; C _D =6 пФ	SOT346,SC59	
	RB411D		shd	V _B <20 B; I _F <500 mA; V _F (I _F =500 mA)<500 mB; C _D =20 πΦ	SOT346,SC59	
D3J	RB706D-40	ROHM	shd×2	V _R <40 B; I _F <30 мA; V _F (I _F =1 мA)<370 мB; C _D =2 пФ	SOT346,SC59	
D3p	BCW33	PHIL	npn	V _{CB0} =32B; I _C =100 MA; P ₀ =250 MBr; h ₂₁ =420800; f _T >100 MFц	SOT23,SOD23	
D3t	BCW33	PHIL	npn	$V_{CB0}=32B$; $I_C=100$ MA; $P_0=250$ MBT; $h_{21}=420800$; $f_T>100$ MF $_{LL}$	SOT23,SOD23	
D4	AZ23B3V6	VISH	dz×2	Vz=3.533.67 B; Rz(Iz=5 mA) < 95 Om	SOT23,SOD23	-
D4	AZ23C3V6	VISH	dz×2	Vz=3.43.8B; Rz(Iz=5 mA) < 95 Om	SOT23,SOD23	
D4	AZ23C3V6	TSC	dz×2	V2=3.43.8 B; R2(I2=5 MA) < 95 OM	SOT23,SOD23	
D4	BCW31R	PHIL	npn	$V_{CB0}=32B$; $I_C=100$ mA; $P_0=350$ mBt; $h_{21}=110220$; $f_T>100$ MF $_{LL}$	SOT23,SOD23	
D4	BCW31R	ZETEX	npn	V_{CB0} =32B; I_C =100 MA; P_0 =330 MBT; h_{21} =110220; f_T >300 MF $_{LL}$	SOT23,SOD23	
D4	HSMP3804	HP	pin×2	I _F <1 A; V _{BR} >100B; R _S <2.0 Ом; С _D <0.37 пФ; R _H >1000 Ом; R _L <8 Ом	SOT23,SOD23	
D46	BAT46W	STM	shd	V _R <100 B; I _F <150 мА; V _F (I _F =10 мА)<0.45 мВ; С ₀ =10 пФ	SOT323,SC70	
D49	CMPD5001S	CSI	dih×2	$I_{E}\text{=}400\text{mA};V_{R}\text{=}120\text{B};V_{E}\{I_{E}\text{=}100\text{mA}\}\text{<}0.9\text{B};I_{R}\text{<}100\text{mA};t_{BR}\text{<}50\text{hc};C_{T}\text{<}35\text{n}\Phi$	SOT23,SOD23	
D5	AZ23B3V9	VISH	dz×2	Vz=3.823.98 B; Rz(Iz=5 mA) < 95 Om	SOT23,SOD23	
D5	AZ23C3V9	VISH	dz×2	Vz=3.74.1B; Rz(Iz=5 мA)<95 Ом	SOT23,SOD23	
D5	AZ23C3V9	TSC	dz×2	Vz=3.74.1B; Rz(Iz=5mA)<950m	SOT23,SOD23	K1-K2-A1,A2





Код	Типономинал	Б	Φ	Особенности	Корпус	Ц: 1•2•3
D5	BCW32R	PHIL	npn	V _{св0} =32 B; I _с =100 мА; P ₀ =350 мВт; h ₂₁ =200450; f ₇ > 100 МГц	SOT23,SOD23	E·B·C
D5	BCW32R	ZETEX	npn	V _{св0} =32 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =200450; f _T >300 МГц	SOT23,SOD23	B·E·C
D53	CMPD2004	CSI	fid	$I_{\rm s}$ <225 μA; $V_{\rm R}$ =240 B; $V_{\rm f}$ ($I_{\rm F}$ =100 μA)<1.0 B; $I_{\rm f}$ <100 μA; $I_{\rm fR}$ <50 μc; $C_{\rm T}$ <5.0 π Φ	SOT23,SOD23	A+n.c.+K
D58	FLLD258	ZETEX	d×2	V _R <100 B; I _F <250 mA; V _E (I _F =200 mA)<1.4 B; I _R <5 mkA; C _D <4 пФ	SOT23,SOD23	A1 · A2 · K1, K2
D5s	BBY57-05W	INF	var	V _R <10 B; I _F <20 мA; I _R <0.01 мкА; С _{1 B} =16.518.6 пФ; С _{4 B} =3.55.5 пФ	SOT323,SC70	A1-A2-K1,K2
D6	AZ23B4V3	VISH	dz×2	Vz=4.214.39 B; R _X (Iz=5 mA) < 95 Om	SOT23,SOD23	K1-K2-A1,A2
D6	AZ23C4V3	VISH	dz×2	V ₂ =4.04.6B; R ₂ (I ₂ =5mA) < 950m	SOT23,SOD23	K1-K2-A1,A2
D6	AZ23C4V3	TSC	dz×2	V ₂ =4.04.6B; R ₂ (I ₂ =5mA)<950m	SOT23,SOD23	K1-K2-A1,A2
D6	BCW33R	PHIL	non	V _{сво} =32 B; I _c = 100 мA; P _D =350 мВт; h ₂₁ =420800; f _T >100 МГц	SOT23,SOD23	E·B·C
D6	BCW33R	ZETEX	non	V _{сво} =32B; I _с =100мA; P _о =330мBт; h _{о1} =420800; f _T >300МГц	SOT23,SOD23	B·E·C
D6	MMBC1622D6	MOT	non	V _{CR0} =40 B; I _C = 100 mA; P _D =300 mBT; h ₂₁ =200400	SOT23,SOD23	B·E·C
D63	FLLD263	ZETEX	d×2	V _B <100 B; I _E <250 mA; V _E (I _E =200 mA)<1.4 B; I _B <5 mkA; C _B <4 πΦ	SOT23,SOD23	
D7	AZ23B4V7	VISH	dz×2	V ₂ =4.614.79 B; R ₂ (I ₂ =5 mA) < 78 Om	SOT23.SOD23	K1-K2-A1.A2
D7	AZ23C4V7	VISH	dz×2	V ₂ =4.45.0B; R ₂ (I ₂ =5mA)<780m	SOT23.SOD23	K1-K2-A1.A2
D7	AZ23C4V7	TSC	dz×2	V ₂ =4.45.0B; R ₂ (I ₂ =5mA)<780m	SOT23.SOD23	K1-K2-A1.A2
D7	MMBC1622D7	MOT	non	V _{CR0} =40 B; I _C = 100 mA; P _D =300 mBT; h ₂₁ =300600	SOT23 SOD23	
D73	BAT54W	STM	shd	V _R <30B; I _e <300 mA; V _e (I _e =100 mA)<0.9B; I _R <1 mκA; C _n <10 nΦ; t _{RR} <5 HC	SOT323,SC70	
D74	BAT54AW	STM	shd×2	$V_R < 30B$; $I_E < 300$ mA; $V_E (I_{E^2} 100$ mA) < 0.9 B; $I_R < 4.0$ mvA; $C_D < 10$ n Φ , $I_{BB} < 5$ HC	S0T323,SC70	
D76	BAR18	ALLEG	shd	$V_{BB} > 70B$; $V_{e}(I_{E}=1 \text{ mA}) < 0.41B$; $I_{B} < 200 \text{ mA}$; $C_{T} < 1.7 \text{ m}$	SOT23,SOD23	A·n.c.·K
D76	BAR18	STM	shd	V _{BR} >70B; V _E (I _E =1 mA)<0.41B; I _B <200 hA	SOT23,SOD23	A·n.c.·K
D76	CMPD6263	CSI	shd	Ic=15 мA; V _{RBM} =70 B; V _E (Ic=1 мA) < 0.3950.410 B; I _R < 200 нА; С _Т < 2.0 пФ	SOT23,SOD23	A·n.c.•K
D77	BAT54CW	STM	shd×2	V ₀ < 30 B; I _c < 300 mA; V _c (I _c = 100 mA) < 0.9 B; I _p < 1 mkA; C ₀ < 10 πΦ; t _{pp} < 5 нс	SOT323,SC70	A1-A2-K1,K2
D77	BCF32R	PHIL	non	V _{CR0} =20B; I _C =200 mA; P _D =200 mBT; h ₂₁ =200; f _T >300 MF _U	SOT23,SOD23	E-B-C
D78	BAT54SW	STM	shd×2	V _B <30B; I _E <300 mA; V _E (I _E : 100 mA)<0.9 B; I _B <1 mkA; C _D <10 nΦ; t _{BB} <5 HC	SOT323.SC70	A1-K2-K1.A2
D7p	BCF32	PHIL	non	V _{CR0} =32B; I _C =100мA; P _D =250мBr; h ₂₁ =200450; f _T >100МГц	SOT23.SOD23	B·E·C
D7t	BCF32	PHIL	non	V _{спо} =32B; I _C =100 мA; P _D =250 мВт; h ₂₁ =200450; f _T >100 МГц	SOT23.SOD23	B·E·C
D8	AZ23B5V1	VISH	dz×2	V ₇ =5.05.2B; R ₇ (I ₂ =5mA)<600m	SOT23.SOD23	K1-K2-A1-A2
D8	AZ23C5V1	VISH	dz×2	V _Z =4.85.4B; R _Z (I _Z =5mA) < 60 Om	SOT23.SOD23	
D8	AZ23C5V1	TSC	dz×2	V ₂ =4.85.4B; R ₂ (I ₂ =5mA) < 60 Om	SOT23.SOD23	
D81	BCF33R	PHIL	non	V _{CR0} =20 B; I _C =200 mA; P _D =200 mBT; h ₂₁ =420; f _T >300 MFu	SOT23.SOD23	
D84	BAT54A	STM	shd×2	$V_R < 30B$; $I_F < 300$ mA; $V_F (I_{F^2} 100$ mA) < 0.9 B; $I_R < 4.0$ mvA; $C_D < 10$ n Φ ; $I_{FR} < 5$ nc	SOT23,SOD23	
D86	BAT54	STM	shd	V _B <30 B; I _E <300 mA; V _E (I _E =100 mA)<0.9 B; I _B <1 mkA; C _D <10 mΦ; t _{BB} <5 HC	SOT23,SOD23	A·n.c.•K
D87	BAT54C	STM	shd×2	V_R < 30 B; I_F < 300 mA; V_F (I_F = 100 mA) < 0.9 B; I_R < 4.0 mrA; C_0 < 10 n Φ ; t_{BR} < 5 Hc.	S0T23,S0D23	A1-A2-K1,K2
D88	BAT54S	STM	shd×2	V_B < 30 B; I_F < 300 mA; V_F (I_F = 100 mA)< 0.9 B; I_R < 4.0 mkA; C_D < 10 n Φ ; I_{BB} < 5 Hc	SOT23,SOD23	A1•K2•K1,A2
D8p	BCF33	PHIL	npn	V _{CB0} =32 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =420800; f _T > 100 МГц	SOT23,SOD23	0.0000000000000000000000000000000000000
D9	1SS401	TOSH	shd	V _R >20B; V _E (I _F =300 мA)<0.45 B; I _E (V _B =20B)<50 мкА; С _Т =46 пФ	SOT323,SC70	
D9	AZ23B5V6	VISH	dz×2	Vz=5.495.71 B; Rz{Iz=5 mA}<40 Om	SOT23,SOD23	K1-K2-A1,A2
D9	AZ23C5V6	VISH	dz×2	V _Z =5.26.0B; R _Z (I _Z =5 mA) < 40 Om	SOT23,SOD23	
D9	AZ23C5V6	TSC	dz×2	V _Z =5.26.0B; R _Z (I _Z =5mA) < 40 Om	SOT23,SOD23	
D94	BAR42	STM	shd	$V_{BR}>30B$; $V_{E}(I_{F}=50 \text{ MA})<0.65B$; $I_{R}<100 \text{ MKA}$; $C_{T}=7 \text{ m}\Phi$	SOT23,SOD23	A+n.c.+K
D95	BAR43	STM	shd	V _{BR} >30 B; V _F (I _F =15 мA)<0.45 B; I _R <100 мкА; С _Т =7 пФ	SOT23,SOD23	A·n.c.·K
D95	CMPSH3	CSI	shd	I _F =100 мА; V _{RRM} =30 B; V _F (I _F =100 мА)<1.0 B; I _R <500 нА; С _Т =7.0 пФ	SOT23,SOD23	A+n.c.+K
D96	BAS70-04	STM	shd×2	V _{BR} >70B; V _E (I _F =1 mA)<0.41B; I _R <200 hA	SOT23,SOD23	A2+K1+K2,A1
D96	CMPD6263S	CSI	shd×2	I _F =15 MA; V _{RRM} =70 B; V _F (I _F =1 MA) < 0.3950.410 B; I _R < 200 HA; C _T < 2.0 пФ	SOT23,SOD23	A2-K1-K2,A1
D97	BAS70-05	STM	shd×2	V _{BR} >70B; V _F (I _F =1 mA)<0.41B; I _B <200 hA	SOT23,SOD23	A2-A1-K2,K1
D97	CMPD6263C	CSI	shd×2	I _F =15 MA; V _{RBM} =70 B; V _F (I _F =1 MA) < 0.3950.410 B; I _R < 200 HA; C _T < 2.0 nΦ	SOT23,SOD23	A2+A1+K2,K1
D98	BAS70-06	STM	shd×2	V _{BR} >70B; V _E (I _E =1 mA)<0.41B; I _B <200 hA	SOT23,SOD23	K2-K1-A2,A1
D98	CMPD6263A	CSI	shd×2	I _E =15 MA; V _{RBM} =70 B; V _E (I _E =1 MA) < 0.3950.410 B; I _R < 200 HA; C _T < 2.0 nΦ	SOT23.SOD23	

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
DA	BCW67A	ALLEG	pnp	V _{CB0} =45B; I _{CB0} <20 HA; h ₂₁ =100250; V _{CE(sat)} <0.7 B; f _T >100 MFu	SOT23,SOD23	B-E-C
DA	BCW67A	CDIL	pnp	V _{CB0} =45B; I _C =800 мA; P _D =330 мВт; h ₂₁ =100250; f _T >100 МГц	SOT23,SOD23	B-E-C
DA	BCW67A	ZETEX	pnp	V ₀₈₀ =45B; I _C =800 мA; P _D =330 мВт; h ₂₁ =100250; f _T >100 МГц	SOT23,SOD23	B-E-C
DA	MMBZ4708	VISH	dz	V ₂ (I _{ZT} =50 mKA)=20.923.1 B; I _B < 0.01 mKA	SOT23,SOD23	A·n.c.·K
DA2	CMPD5001	CSI	dih	$I_{E^{\pm}}400\text{mA};V_{R^{\pm}}120B;V_{F}(I_{E^{\pm}}100\text{mA})\!<\!0.9B;I_{R}\!<\!100\text{hA};t_{BR}\!<\!50\text{hc};C_{T}\!<\!35\text{n}\Phi$	SOT23,SOD23	A·n.c.·K
DA5	BAR43S	STM	shd×2	$V_{BR} > 30 B; V_{E}(I_{E}=15 \text{ mA}) < 0.45 B; I_{R} < 100 \text{ m/sA}; C_{T}=7 \text{ m}\Phi$	SOT23,SOD23	A2+K1+K2,A1
DA5	CMPSH3S	CSI	shd×2	I_{e}^{-1} 100 MA; V_{PPM}^{-3} 30 B; $V_{e}(I_{e}^{-1}100$ MA) < 1.00 B; I_{R} < 500 HA; C_{T}^{-2} 2.0 n Φ ; t_{BR} < 5.0 Hc	SOT23,SOD23	A2+K1+K2,A1
DAs	BCW67A	SIEM	pnp	V _{CB0} =45 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =100250; f _T =200 МГц	SOT23,SOD23	B-E-C
DB	BCW67B	ALLEG	pnp	V _{CB0} =45 B; I _{CB0} <20 нA; h ₂₁ =160400; V _{CE(sat)} <0.7 B; f _T >100 МГц	SOT23,SOD23	B-E-C
DB	BCW67B	CDIL	pnp	V _{CB0} =45 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =160400; f _T >100 МГц	SOT23,SOD23	B-E-C
DB	BCW67B	ZETEX	pnp	V _{CB0} =45B; I _C =800 мA; P _D =330 мBт; h ₂₁ =160400; f _T >100 MFu	SOT23,SOD23	B-E-C
DB	BCW67B	SGS	pnp	V _{CB0} =45B; I _C =800 мA; P _D =330 мВт; h ₂₁ =160400; f _T >100 МГц	SOT23,SOD23	B-E-C
DB1	BAR43A	STM	shd×2	V _{BB} >30B; V _E (I _E =15 MA) < 0.45B; I _B < 100 MKA; C _T =7 mΦ	SOT23,SOD23	K2·K1·A1,A2
DB1	CMPSH3A	CSI	shd×2	I_F =100 mA; V_{PPM} =30 B; V_F (I_F =100 mA)<1.00 B; I_R <500 πA; C_T =2.0 π Φ ; t_{BR} <5.0 πC	SOT23,SOD23	K2 · K1 · A2,A1
DB2	BAR43C	STM	shd×2	$V_{BR} > 30 \text{ B}; V_{e}(I_{e}=15 \text{ mA}) < 0.45 \text{ B}; I_{B} < 100 \text{ m/A}; C_{T}=7 \text{ m}\Phi$	SOT23,SOD23	A2+A1+K1,K2
DB2	CMPSH3C	CSI	shd×2	I_F 100 μA; V_{FFM} =30 B; V_F (I_F = 100 μA) < 1.00 B; I_R < 500 μA; C_T = 2.0 π Φ ; t_{BR} < 5.0 μc.	SOT23,SOD23	A2+A1+K2,K1
DB6	BAT46AW	STM	shd×2	V _B <100 B; I _F <150 мА; V _F (I _F =10 мА)<0.45 мВ; С _D =10 пФ	SOT323,SC70	K2·K1·A1,A2
DB6	CMPD2004S	CSI	fih×2	I_{e} <225 mA; V_{R} =240 B; V_{e} (I_{e} =100 mA) < 1.0 B; I_{R} <100 нA; t_{RR} <50 нc; C_{T} <5.0 n Φ	SOT23,SOD23	A2+K1+K2,A1
DBs	BCW67B	SIEM	pnp	V _{CB0} =45B; I _C =800 мA; P _D =330 мВт; h ₂₁ =160400; f _T =200 МГц	SOT23,SOD23	B-E-C
DC	BCW67C	CDIL	pnp	V _{CBO} =45B; I _C =800 мA; P _D =330 мВт; h ₂₁ =250630; f _T >100 МГц	SOT23,SOD23	B-E-C
DC	BCW67C	ZETEX	pnp	V _{сва} =45 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =250630; f _T >100 МГц	SOT23,SOD23	B-E-C
DC	BCW67C	SGS	onp	V _{сво} =45 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =250630; f _T >100 МГц	SOT23,SOD23	B-E-C
DC	MMBZ4695	VISH	dz	V ₂ (I ₂₇ =50 mKA)=8.279.14 B; I _B < 1 mKA	SOT23,SOD23	A·n.c.·K
DCs	BCW67C	SIEM	ono	V ₀₈₀ =45 B; I _C =800 мA; P ₀ =330 мВт; h ₂₁ =250630; f ₁ =200 МГц	SOT23,SOD23	B·E·C
DD	2SC2463D	REN	npn	V _{CB0} =55 B; I _C =100 mA; P _D =150 mBT; h ₂₁ =250500	SOT23,SOD23	B-E-C
DD	MMBZ4696	VISH	dz	V ₂ (I ₂₇ =50 mKA)=8.659.56 B; I _B < 1 mKA	SOT23,SOD23	A·n.c.·K
DE	2SA1037AKLNE	ROHM	onp	V _{CB0} =50 B; I _C = 150 мA; P ₀ = 200 мВт; h ₂₁ =390820; f ₁ > 140 МГц	SOT346,SC59	B·E·C
DE	2SC2463E	REN	npn	V _{CB0} =55B; I _C =100 MA; P _D =150 MBT; h ₂₁ =400800	SOT23,SOD23	B-E-C
DE	MMBZ4697	VISH	dz	V ₂ (I ₂₇ =50 MKA)=9.510.5 B; I _B < 1 MKA	SOT23,SOD23	
DF	BCW68F	ALLEG	ono	V _{CB0} =60 B; I _{CB0} <20 HA; h ₂₁ =100250; V _{CE(sat)} <0.7 B; f _T >100 MFu	SOT23,SOD23	
DF	BCW68F	CDIL	ano	V _{C80} =60 B; I _C =800 мА; P _D =330 мВт; h ₂₁ =100250; f _T >100 МГц	SOT23.SOD23	B-E-C
DF	BCW68F	ZETEX	ono	V _{cs0} =60 B; I _c =800 мA; P _D =330 мВт; h ₂₁ =100250; f _T >100 МГц	SOT23.SOD23	B-E-C
DF	BCW68F	SGS	ono	V _{CB0} =60 B; I _C =800 MA; P _D =330 MBT; h ₂₁ =100250; f _T >100 MFц	SOT23,SOD23	B-E-C
DF	MMBZ4698	VISH	dz	V ₂ (I _{2T} =50 mKA)=10.511.6 B; I _B < 0.05 mKA	SOT23.SOD23	A CONTRACTOR OF THE PARTY OF TH
DFs	BCW68F	SIEM	ono	V _{CB0} =60 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =100250; f _T =200 МГц	SOT23.SOD23	B-E-C
DG	BCW68G	ALLEG	ono	V _{CB0} =60B; I _{CB0} <20 HA; h ₂₁ =160400; V _{CE(sat)} <0.7B; f _T >100 MFu	SOT23,SOD23	B-E-C
DG	BCW68G	CDIL	onp	V _{CB0} =60 B; I _C =800 mA; P _D =330 mBt; h ₂₁ =160400; f _T >100 MFu	SOT23,SOD23	
DG	BCW68G	ZETEX	onp	V _{CBB} =60 B; I _C =800 мA; P _D =330 мBт; h ₂₁ =160400; f _T >100 MFu	SOT23,SOD23	
DG	BCW68G	SGS	onp	V _{CB0} =60 B; I _C =800 mA; P _D =330 mBr; h ₂₁ =160400; f _T >100 MFu	SOT23,SOD23	
DG	BRC124ECM	REN	Dnpn	V _{CC} =50B; I _{CVC} =100 MA; P _D =150 MBT; h _{P1} >56; 22 к/22 к	SOT323,SC70	
DG	BRC124EMP	REN	Dnpn	V _{CC} =50B; I _{CCC} =100 MA; P _D =150 MBT; h _{P1} >56; 22 к/22 к	SOT23,SOD23	10/2/2015/99
DGs	BCW68G	SIEM	ono	V _{CB0} =60 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =160400; f _T =200 МГц	SOT23,SOD23	10000
DH	BCW68G	MOT	pnp	V _{D80} =60 B; I _C =800 MA; P _D =330 MBT; h ₂₁ =160400; f _T >100 MFц	SOT23,SOD23	100.00
DH	BCW68H	CDIL	ono	V _{CB0} =60 B; I _C =800 MA; P _D =330 MBT; h ₂ I=250630; f _T > 100 MFu	SOT23,SOD23	
DH	BCW68H	ZETEX	onp	V _{CB0} =60 B; I _C =800 MA; P _D =330 MBT; h ₂₁ =250630; f _T >100 MFц	SOT23,SOD23	
DH	BCW68H	SGS	ono	V _{DB0} =60 B; I _C =800 MA; P _D =330 MBT; h ₂₁ =250630; f _T > 100 MFц	SOT23,SOD23	70000000
DH	MMBD2000T1	MOT	di	V _R <30 B; I _c <200 mA; V _E (I _c =10 mA)<0.95 B; C _D <2 nΦ; I _{RR} <3 nc	S0T323,SC70	
DH	MMBZ4699	VISH	dz	V ₂ (I ₂₇ =50 nicA)=11.412.6 B; I _B <0.05 nicA	SOT23,SOD23	2222





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
DHs	BCW68H	SIEM	pnp	V _{CB0} =60 B; I _C =800 mA; P _D =330 mBT; h ₂₁ =250630; f _T =200 MFu	SOT23,SOD23	B·E·C
DI	2SC3867	REN	non	VCBE=20 B; I _C =50 mA; P _D =150 mBT; h _{D1} =20200; f _T >1.4 FF _{LL}	SOT346,SC59	E·B·C
DI	MMBD2005T1	MOT	di×2	V _B <30B; I _E <200 mA; V _E (I _E =10 mA)<0.95 B	SOT323,SC70	K1 · K2 · A1, A2
DJ	MMBZ4700	VISH	dz	V ₄ (I ₂₇ =50 mKA)=12.413.7 B; I _b < 0.05 mKA	SOT23.SOD23	A·n.c.·K
DK	MMBZ4701	VISH	dz	V ₄ (I ₂₇ =50 mKA)= 13.314.7 B; I _B < 0.05 mKA	SOT23 SOD23	150 10100000000000000000000000000000000
DKs	BCX42	SIEM	pnp	V _{сво} =125B; I _C =800 мА; Р _о =330 мВт; h ₂₁ >63; f ₇ =150 МГц	SOT23,SOD23	B-E-C
DM	MMBZ4702	VISH	dz	V _X (I ₂₇ =50 mKA)= 14.315.8 B; I _B < 0.05 mKA	SOT23,SOD23	12770000000
DN	2SK3349	REN	nMOS	V _{DS} =20B; I _D =50 mA; P _D =100 mBT; R _{DS(on)} < 7.2 Om	SOT416 SC75A	100000000000000000000000000000000000000
DN	MMBZ4703	VISH	dz	V _X (I _{ZT} =50 mxA)= 15.216.8 B; I _R <0.05 mxA	SOT23 SOD23	
DP	2SJ587	REN	pMOS	ELEI I	S0T416.SC75A	
DP	MMBD2010	MOT	di×2	V _B <30B; I _E <200 мA; V _E (I _E =10 мA)<0.95 B; C ₀ <2 nΦ; t _{BB} <3 HC	SOT23,SOD23	
DP	MMBZ4704	VISH	dz	V ₂ (I ₂₇ =50 mrA)=16.217.9B; I _R <0.05 mrA	SOT23.SOD23	
DQ.	2PB1219AQ	PHIL	ono	V _{CF0} =60 B; I _C =500 мA; P _D =200 мВт; h ₂₁ =85170; f _T >100 МГц	SOT323.SC70	200000000000000000000000000000000000000
DQ.	2PB710AQ	PHIL	ono	V _{CH1} =50 B; I _C =500 MA; P _D =250 MBT; h ₂₁ =85170; f _T >100 MF _L	SOT346,SC59	
DR	2PB1219AR	PHIL	onp	V _{CF0} =60 B; I _C =500 MA; P _D =200 MBr; h ₂₁ =120240; f _T > 120 MFu	SOT323.SC70	
DR	2PB710AR	PHIL	ono	V _{CRI} =50 B; I _C =500 MA; P _D =250 MBT; h ₂₁ =120240; f _T >120 MFц	SOT346.SC59	
DR	2SA1037AKLNR	ROHM	onp	V _{CBD} =50 B, I _C =150 MA, P _D =200 MBr, I _{P2} =180390; f _T >140 MFц	SOT346,SC59	
DR	BCW60BR	ZETEX	non	V _{CB0} =32B; I _C =200mA; P _D =330mBr; h ₂₁ =180310; f _T >250MFu	SOT23,SOD23	
DS	2PB1219AS	PHIL	pnp	V _{CER} =60 B; I _C =500 MA; P _D =200 MBr; h _{Pl} =170340; f _T > 140 MF _U	SOT323,SC70	120.000.000
DS	2PB710AS	PHIL	ono	V _{CED} -50 В; I _C -500 мА; Р _D -250 мВт; I _{P2} -170340; I _T >140 МГц	SOT346.SC59	10.100/10.000
DS DS	2SA1037AKLNS	ROHM	onp	V _{CBD} -50 B; I _C =150 мA; P _D =250 мB; r _{I21} =170540; г _I >140 мГц	SOT346,SC59	180,000,00
DT	BCW67AR	SGS	onp	V _{CBO} -30 B, I _C -130 MA, P _D -200 MBT, I _{R21} -270350, I _T > 140 MTц V _{CBO} -45 B; I _C -800 MA; P _D -330 мBT; I _{R21} -270250; f _T > 100 МГц	SOT23.SOD23	
DT	MMBZ4705	VISH		V ₂ (I ₂₇ =50 mkA)= 17.118.9 B; I _B <0.05 mkA		
DU	BCW67BR	SGS	dz	2.21	SOT23,SOD23	
			pnp	V _{CB0} =45B; I _C =800 мA; P _D =330 мBτ; h ₂₁ =160400; f _T >100 MΓц	SOT23,SOD23	C-02-1-
DU	MMBZ4706	VISH	dz	V _Z (I _{ZT} =50 mKA)=18.120.0 B; I _R <0.05 mKA	SOT23,SOD23	LOSS SECTIONS OF THE PARTY.
DV	MMBZ4707	VISH	dz	V _Z (I _{ZT} =50 mkA)=19.021.0 B; I _R <0.01 mkA	SOT23,SOD23	
DW	BCW67CR	SGS	pnp	V _{CB0} =45B; I _C =800мA; P _D =330мBт; h ₂₁ =250630; f _T >100МГц	SOT23,SOD23	
DX	BCW68FR	SGS	pnp	V _{CB0} =60 B; I _C =800 мA; P _D =330 мBт; h ₂₁ =100250; f _T >100 МГц	SOT23,SOD23	
DY	BCW68GR	SGS	pnp	V _{CB0} =60 B; I _C =800 мA; P ₀ =330 мВт; h ₂₁ =160400; f _T >100 МГц	SOT23,SOD23	
DY	MMBZ4710	VISH	dz	V _Z (I _{ZT} =50 mKA)=23.826.3 B; I _R <0.01 mKA	SOT23,SOD23	2001703000000000000000000000000000000000
DZ	BCW68HR	SGS	pnp	V_{CB0} =60 B; I_C =800 mA; P_D =330 mBT; h_{21} =250630; f_T >100 M Γ_{IJ}	SOT23,SOD23	500 St. 100
DZ	MMBZ4709	VISH	dz	V _Z (I _{ZT} =50 mkA)=22.825.2 B; I _R <0.01 mkA	SOT23,SOD23	100000000000000000000000000000000000000
E	1SS780	ROHM	SW	40B; 100mAloleakage	SOT416,SC75	1.00.00
E	IRLML6402	IR	pMOS	HEXFET; V _{DS} =20 B; I _D =2.2A; P _D =1.3 BT; R _{DS(on)} < 0.135 O _M	SOT23,SOD23	
E0	HSMP3810	HP	pin	$I_F \le 1 A; V_{BR} \ge 100 B; R_S \le 3.00 m; C_D \le 0.35 n\Phi; R_H \ge 1500 0 m; R_L \le 10 0 m$	SOT23,SOD23	
E0	HSMP381B	HP	pin	$I_F \le 1A$; $V_{BR} \ge 100B$; $R_T \le 3.0 \text{ OM}$; $CT \le 0.35 \text{ m}$; $R_H \ge 1500 \text{ OM}$; $R_L \le 10 \text{ OM}$	SOT323,SC70	
E1	BFS17	ZETEX	npn	V _{CB0} =25B; I _C =25мA; P _D =330мВт; h ₂₁ =25150; f _T >1000МГц	SOT23,SOD23	13.000.00
E1	BFS17	TELEF	npn	V _{CB0} =25B; I _C =25мA; P _D =200мВт; h ₂₁ =20150; f _T >1000МГц	SOT23,SOD23	20000000
E1	BFS17LT1	MOT	npn	V_{CB0} =15B; I_C =50 mA; P_0 =200 mBT; h_{21} =20150; f_T >1000 M Γ_{LL}	SOT23,SOD23	B·E·C
E1	HSMP3811	HP	pin	$I_F \le 1A; V_{BR} \ge 100B; R_S \le 3.00m; C_D \le 0.35 \text{n} \Phi; R_H \ge 1500 \text{Om}; R_L \le 10 \text{Om}$	SOT23,SOD23	100000000000000000000000000000000000000
Εí	MMBZ5231BT	DIODS	dz	V _Z (I _{ZT} =20 mA)=4.855.36 B; I _R <5 mкA	SOT523	A+n.c.+K
E11	DTA113ZE	ROHM	Dpnip	V_{CB0} =50 B; I_C =100 mA; P_D =150 mBr; h_{21} >33; f_1 >250 MFq; R_1/R_2 =1/10 kOm	SOT416,SC75A	
E11	DTA113ZKA	ROHM	Dpnp	V_{C80} =50 B; I_C =100 mA; P_D =200 mBr; h_{21} >33; f_T >250 MFu; R_1/R_2 =1/10 кОм	SOT346,SC59	B-E-C
E13	DTA143ZE	ROHM	Dpnp	V_{CB0} =50 B; I_0 =100 MA; P_0 =150 MB τ ; h_{21} >80; f_7 >250 MF ι ; R_1/R_2 =4.7/47 KOM	SOT416,SC75A	B·E·C
E13	DTA143ZKA	ROHM	Dpnjo	$V_{\rm CB0}$ =50 B; $I_{\rm G}$ =100 MA; $P_{\rm D}$ =200 MBT; h_{21} >80; $f_{\rm T}$ >250 MFu; $R_{\rm T}/R_{\rm 2}$ =4.7/47 kOM	SOT346,SC59	B·E·C
E1H	BFS17H	ZETEX	npn	V_{CB0} =25B; I_C =25MA; P_D =330MBT; h_{21} =70200; f_T >1000MFu	SOT23,SOD23	B-E-C
E1L	BFS17L	ZETEX	npn	V _{CB0} =25B; I _C =25мA; P _D =330мBт; h ₂₁ =25100; f _T >1000МГц	SOT23,SOD23	B-E-C
E10	KSC2859	SAMS	npn	V _{CB0} =35B; I _C =500 мA; P ₀ =150 мВт; h ₂₁ =70140; f _T >300 МГц	SOT23,SOD23	B-E-C
E1p	BFS17	PHIL	npn	$V_{CB0}^{-25B}; I_C^{-25mA}; P_D^{-330mBT}; h_{21}^{-25150}; f_T > 1000 MFq$	SOT23,SOD23	B-E-C
E1p	BFS17W	PHIL	non	V _{сво} =25B; I _с =25мA; P _о =330мВт; h ₂₁ =25150; f _T >1000МГц	SOT323,SC70	B·E·C

Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
E1Y	KSC2859	SAMS	npn	V _{G80} +35B; I _C +500 MA; P _D +150 MBT; h ₂₁ +120240; f _T >300 MFu	SOT23,SOD23	B·E·C
E2	BAL99	ZETEX	di	V _B <70B; I _E <100mA; V _E (I _E :50mA)<1.1B; I _B <2.5mkA; C _D <1.5nΦ; t _{BB} <6hc	SOT23,SOD23	n.c. · K·A
E2	BFS17A	TELEF	non	V _{сво} =25B; I _c =25мA; P _n =200 мВт; h ₂₁ =20150; f _T >1000 МГц	SOT23.SOD23	B-E-C
E2	HSMP3812	HP	pin×2	$I_{E} \le 1A$; $V_{BB} \ge 100B$; $R_{S} \le 2.0$ OM; $C_{D} \le 0.37$ n Φ ; $R_{H} \ge 1000$ OM; $R_{L} \le 8$ OM	SOT23,SOD23	A1-K2-K1.A2
E2	HSMP381C	HP	oin×2	I _E <1A; V _{BB} >100B; R _T <3.00m; CT<0.35πΦ; R _U >1500 0m; R _I <10 0m		A1-K2-A2,K1
E2	MMBZ5232BT	DIODS	dz	V ₂ (I ₂₇ =20 mA)=5.325.88B; I _R <5 mkA	SOT523	A·n.c.·K
E21	DTC113ZE	ROHM	Dnon	V _{CB0} =50 B; I _C =100 mA; P _D =150 mBr; h ₂₁ >33; f _T >250 MFu; R ₁ /R ₂ =1/10 kOm	SOT416.SC75A	
E21	DTC113ZKA	ROHM	Dnpn	V _{CB0} =50B; I _C =100 mA; P _D =200 mBt; h ₂₁ >33; f _T >250 MFu; R ₁ /R ₂ =1/10 kOm		B-E-C
E23	DTC143ZCA	ROHM	Dnpn	V _{DB0} = 50 B; I _C = 100 MA; P _D = 150 MBT; h ₂₁ > 80; I _T > 250 MFu; R ₇ /R ₉ = 4.7/47 KOM	SOT23,SOD23	
E23	DTC143ZE	ROHM	Dnpn	V_{C80} :50 B; I_C : 100 kA; P_D : 150 kBr; h_{21} >80; f_T >250 MFu; R_1/R_2 :4.7/47 kOM	SOT416,SC75A	B-E-C
E23	DTC143ZKA	ROHM	Dnpn	V_{C80} =50 B; I_C = 100 xA; P_D =200 xBr; h_{21} >80; f_T >250 MFu; P_1/P_2 =4.7/47 kOx	SOT346,SC59	B-E-C
E3	1SS190	TOSH	di	V _R <80 B; I _F <100 mA; V _F (I _F =100 mA)<1.2 B; I _R <0.5 mkA; t _{RR} <4 hc	SOT346,SC59	n.c. · K·A
E3	2SA1688	SANYO	pnp	V _{C80} =30 B; I _C =30 mA; P _D =150 mBT; h ₂₁ =60120; f _T >320 MF _U	SOT323,SC70	B-E-C
E3	BAR99	ZETEX	di	$V_B < 70B$; $I_E < 100 \text{ mA}$; $V_E (I_E = 50 \text{ mA}) < 1.1B$; $I_B < 2.5 \text{ mkA}$; $C_D < 1.5 \text{ n}\Phi$; $t_{BB} < 6 \text{ hc}$	SOT23,SOD23	K+n.c.+A
E3	HSMP3813	HP	pin×2	$I_{E} \le 1 A; V_{BR} \ge 100 B; R_{S} \le 2.0 Om; C_{D} \le 0.37 \pi \Phi; R_{H} \ge 1000 Om; R_{L} \le 8 Om$	SOT23,SOD23	K1-K2-A1,A2
E3	HSMP381E	HP	pin×2	I _E <1A; V _{BB} >100B; R _T <3.0 Om; CT<0.35πΦ; R _H >1500 Om; R _L <10 Om	SOT323,SC70	K1-K2-A1,A2
E32	DTA123JE	ROHM	Dpnp	V_{C80} :50B; I _C :100 xA; P _D :150 xBr; h ₂₁ >80; f _T >250 MFu; R ₁ /R ₂ :2.2/47 xOx	SOT416,SC75A	B-E-C
E32	DTA123JKA	ROHM	Dpnp	$V_{\rm CB0}$ =50 B; $I_{\rm C}$ = 100 MA; $P_{\rm D}$ =200 MBT; h_{21} >80; $f_{\rm T}$ >250 MFu; $R_{\rm 1}/R_{\rm 2}$ =2.2/47 KOM	SOT346,SC59	B-E-C
E4	2SA1688	SANYO	pnp	V _{C80} =30 B; I _C =30 mA; P _D =150 mBT; h ₂₁ =90180; f _T >320 MFц	SOT323,SC70	B-E-C
E4	BFS17R	PHIL	npn	V _{CBO} =25B; I _C =25 мA; P _D =330 мВт; h ₂₁ =25150; f _T >1000 МГц	SOT23,SOD23	C·B·E
E4	BFS17R	TELEF	npn	V _{сво} =25B; I _C =25 мA; P _D =200 мВт; h ₂₁ =20150; f _T >1000 МГц	SOT23,SOD23	C-B-E
E4	HSMP3814	HP	pin×2	$I_{e} < 1 \text{ A; } V_{BB} > 100 \text{ B; } R_{s} < 2.0 \text{ Om; } C_{D} < 0.37 \text{ n}\Phi; R_{H} > 1000 \text{ Om; } R_{I} < 8 \text{ Om}$	SOT23,SOD23	A1-A2-K1,K2
E4	HSMP381F	HP	pin×2	I _E <1A; V _{BB} >100B; R _T <3.00m; CT<0.35πΦ; R _H >1500 0m; R _I <10 0m	SOT323,SC70	A1-A2-K1,K2
E4	MMBZ5234BT	DIODS	dz	V ₂ (I ₂₇ =20 mA)=5.896.51 B; I _B <5 mrA	SOT523	A·n.c.·K
E42	DTC123JE	ROHM	Dnpn	V_{CB0} =50 B; I_C =100 xA; P_D =150 xBr; h_{21} >80; f_T >250 MFu; R_T/R_D =2.2/47 xOx	SOT416,SC75A	B-E-C
E42	DTC123JKA	ROHM	Dnpn	V_{C80} =50 B; I_C = 100 MA; P_D =200 MBT; h_{21} >80; f_T >250 MFu; P_1/P_2 =2.2/47 KOM	SOT346,SC59	B-E-C
E42	DTC123JUA	ROHM	Dnpn	V_{C89} =50 B; I_{C} = 100 MA; P_{D} =200 MB τ ; h_{21} >80; f_{T} >250 M Γ u ; P_{1}/P_{2} =2.2/47 KOM	SOT323,SC70	B-E-C
E 5	2SA1688	SANYO	pnp	V_{C80} =30 B; I_C =30 mA; P_0 =150 mBr; h_{21} =135270; f_T >320 M Γ_{II}	SOT323,SC70	B-E-C
E5	BFS17AR	TELEF	npn	V _{CB0} =25B; I _C =25мA; P _D =200 мВт; h ₂₁ =20150; f _T >1000 МГц	SOT23,SOD23	C·B·E
E 5	MMBZ5235BT	DIODS	dz	V ₂ (I _{ZT} =20 mA)=6.467.14 B; I _R < 3 mkA	SOT523	A·n.c.·K
E56	DTA144VE	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =150 mBt; h_{21} >33; f_T >250 MFu; R_1/R_2 =47/10 kOm	SOT416,SC75A	B-E-C
E56	DTA144VKA	ROHM	pnp	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBt; h_{21} >33; f_T >250 MFu; P_1/P_2 =47/10 kOm	SOT346,SC59	B-E-C
E56	DTA144VUA	ROHM	Dpnp	V_{CB0} =50 B; I_C = 100 mA; P_D =200 mBt; h_{21} >33; f_7 >250 MFu; R_1/R_2 =47/10 kOm	SOT323,SC70	B-E-C
E6	ZC2800E	ZETEX	shd	V _R <75B; V _E (I _E =1 мА)<0.41 B; I _R <0.2 мкА; С _D <2.0 пФ	SOT23,SOD23	A·n.c.·K
E66	DTC144VE	ROHM	Dnpn	V_{OB0} =50 B; I_C =100 mA; P_D =150 mBr; h_{21} >33; f_T >250 MFu; R_1/R_2 =47/10 кОм	SOT416,SC75A	B-E-C
E66	DTC144VKA	ROHM	Dnpn	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBt; h_{21} >33; f_T >250 MFu; R_1/R_2 =47/10 kOm	SOT346,SC59	B-E-C
E79	DTA115UK	ROHM	Dpnp	V_{C80} =50 B; I_C =100 MA; P_D =200 MBT; h_{21} >27; f_T >250 MFu,	SOT346,SC59	B-E-C
E8	PDTB123YK	PHIL	Dpnp	V _{CB0} =50 B; I _C =500 мА; P _D =250 мВт; h ₂₁ > 70; 2.2 кОм/10 кОм	SOT346,SC59	B·E·C
E8	ZC2811E	ZETEX	shd	$V_R < 15B$; $V_E (I_F = 1 \text{ mA}) < 0.41 \text{ B}$; $I_R < 0.1 \text{ mkA}$; $C_D < 1.2 \text{ n}\Phi$	SOT23,SOD23	A•n.c.•K
E89	DTC115UK	ROHM	Dnpn	V _{CB0} =50 B; I _C =100 мA; P _D =200 мВт; h ₂₁ >27; f _T >250 МГц	SOT346,SC59	B-E-C
E9	ZC5800E	ZETEX	shd	V _B <50B; V _E (I _E =1 MA)<0.41B; I _B <0.2 MKA; C _D <2.0 nΦ	SOT23,SOD23	A·n.c.·K
E92	DTB123TK	ROHM	Dpnp	V_{C80} =50 B; I_C =500 xA; P_D = 200 xBr; h_{21} =100600; f_T > 200 MFu; R_1 = 2.2 xOm	SOT346,SC59	B-E-C
E94	DTB114TK	ROHM	Dpnp	V _{GB0} =50 B; I _C =500 mA; P _D =200 mBr; h ₂₁ =100600; f _T >200 MFu; R ₁ =10 kOm	SOT346,SC59	B·E·C
E97	DTB163TK	ROHM	Dono	V _{CR0} =50 B; I _C =500 мA; P _D =200 мВт; h ₂₁ >100600; f _T >200 МГц	SOT346,SC59	
EA	BCW65A	ALLEG	non	V _{CB0} =60 B; I _{CB0} <20 нA; h ₂₁ =100250; f _T >100 МГц	SOT23.SOD23	





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
ΕA	BCW65A	CDIL	npn	V _{сво} =60 B; I _с =800 мА; P _о =330 мВт; h ₂₁ =100250; f _T >100 МГц	SOT23,SOD23	B·E·C
EA	BCW65A	ZETEX	non	V _{сво} =60 B; I _c =800 мA; P _D =330 мВт; h _{2t} =100250; f _T >100 МГц	SOT23,SOD23	B·E·C
EA	MMBZ4711	VISH	dz	V ₂ (I ₂₇ =50 mKA)=25.728.4B; I _B <0.01 mKA	SOT23,SOD23	A·n.c.·K
EAs	BCW65A	SIEM	non	V _{спо} =60 B; I _с =800 мА; P _о =330 мВт; h ₂₁ =100250; f _T =170 МГц	SOT23.SOD23	B-E-C
EB	BCW65B	ALLEG	non	V _{CBO} =60 B; I _{CBO} < 20 нА; h ₂₁ =160400; f _T > 100 МГц	SOT23,SOD23	B·E·C
EB	BCW65B	CDIL	non	V _{сво} =60 B; I _с =800 мА; P _о =330 мВт; h _{оз} =160400; f _T >100 МГц	SOT23,SOD23	B·E·C
EB	BCW65B	ZETEX	non	V _{сво} =60 B; I _с =800 мА; P _о =330 мВт; h ₂₁ =160400; f _T >100 МГц	SOT23.SOD23	B·E·C
EB	HSMP4810	HP	pin	I _E <1A; P _D <250 мВт; V _{RR} >100 В; R _S <3.0 Ом; C _D <0.40 пФ; L _T =1.0нГ	SOT23,SOD23	K·K·A
EB	MSC1022-B	MOT	onp	V _{CRD} =20B; f _T =150MF _{LL}	SOT23.SOD23	
	MAX6125EUR	MAX	vref	V _{IN} =2.712.6B; I _{CC} <130 мкА; V _{OUT} =2.5 B	SOT23,SOD23	
EBs	BCW65B	SIEM	non	V _{CR0} =60 B; I _C =800 mA; P _D =330 mBT; h ₂₁ =160400; f _T =170 MFu	SOT23,SOD23	
EC	2SC2732	REN	non	V _{CR0} =30 B; I _C =20 mA; P _D =150 mBτ; h ₂₁ >30; f _T >700 MΓц	SOT346.SC59	100000000000000000000000000000000000000
EC	2SC4462	REN	non	V _{CBD} =30 B; I _C =20 мA; P _D =100 мВт; h ₂₁ >30; f _T >700 МГц	SOT323,SC70	0.00000.000
EC	BCW65C	CDIL	non	V _{CB0} =60 B; I _C =800 MA; P _D =330 MBT; h ₂₁ =250630; f _T >100 MFц	SOT23,SOD23	
EC	BCW65C	ZETEX	non	V _{CB0} =60 B; I _C =800 MA; P _D =330 MB; h ₂₁ =250630; f _T >100 MF _U	SOT23,SOD23	
EC	MMBZ4712	VISH	dz	V _Z (I _{ZT} =50 MKA)=26.629.4B; I _R <0.01 MKA	SOT23,SOD23	
EC	MSC1022-C	MOT	onp	V _{CPO} =20 B: f _T =150 MFu	SOT23,SOD23	
	MAX6141EUR	MAX	yref	V _{IN} =2.712.6B; I _{CC} <130 мкA; V _{CM} =4.096 B	SOT23,SOD23	
ECs	BCW65C	SIEM	non	V _{CR0} =60 B; I _C =800 MA; P _D =330 MBT; h ₂₁ =250630; f _T =170 MFµ	SOT23,SOD23	
ED	MMBZ4713	VISH	dz	V ₂ (I _{2T} =50 m;A)=28.531.5B; I _B <0.01 m;A	SOT23,SOD23	
	MAX6145EUR	1000000		A. C.	SOT23,SOD23	
	MAX6330SUR	MAX	vref	V _{IN} =2.712.6B; I _{CC} <130 мкА; V _{OUT} =4.5B		
ELIAA	MAX53305UH	MAX	reg+ mrc	V _{TR} =2.78 B; V _{OUT} =3.0 B; I _{OUT} >50 мA	SOT23,SOD23	SHUNT
EE	MMBZ4714	VISH	dz	V _Z (I _{ZT} =50 mKA)=31.434.7 B; I _R <0.01 mKA	SOT23,SOD23	A·n.c.·K
EEAA	MAX6150EUR	MAX	vref	V _{IN} =2.712.6B; I _{CC} <130 mrA; V _{OUT} =5.0 B	SOT23,SOD23	IN-OUT-GND
EF	BCW66F	ALLEG	npn	V _{CB0} =75 B; I _{CB0} <20 нА; h ₂₁ =100250; f _T >100 МГц	SOT23,SOD23	B.E.C
EF	BCW66F	CDIL	npn	V _{CB0} =75B; I _C =800 мА; P _D =330 мВт; h ₂₁ =100250; f _T >100 МГц	SOT23,SOD23	B-E-C
EF	BCW66F	ZETEX	npn	V _{CB0} =75 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =100250; f _T >100 МГц	SOT23,SOD23	B-E-C
EF	MMBZ4715	VISH	dz	V _Z (I _{ZT} =50 mKA)=34.237.8 B; I _B <0.01 mKA	SOT23,SOD23	A·n.c.·K
EFAA	MAX6520EUR	MAX	vref	V _{IN} =2.411 B; TC _{VDUT} <50 ppm/°C; V _{DUT} =1.2 B	SOT23,SOD23	VIN-VOUT-
EFs	BCW66F	SIEM	npn	V _{CB0} =75 B; I _C =800 мА; P _D =330 мВт; h ₂₁ =100250; f _T >170 МГц	SOT23,SOD23	
EG	BCW66G	ALLEG	npn	V _{CB0} =75B; I _{CB0} <20 нA; h ₂₁ =160400; f _T >100 МГц	SOT23,SOD23	B·E·C
EG	BCW66G	CDIL	npn	V _{CB0} =75B; I _C =800мA; P _D =330мBт; h ₂₁ =160400; f _T >100МГц	SOT23,SOD23	B·E·C
EG	BCW66G	ZETEX	npn	V _{CB0} =75B; I _C =800 мA; P _D =330 мВт; h ₂₁ =160400; f _T >100МГц	SOT23,SOD23	B-E-C
EG	BRA114ECM	REN	Dpnp	V _{CC} =50 B; I _{OUT} =100 mA; P _D =150 mBT; h ₂₁ >30; 10 к/10 к	SOT323,SC70	B·E·C
EG	BPA114EMP	REN	Dpnp	V _{CC} =50 B; I _{CUT} =100 мА; P _D =150 мВт; h ₂₁ >30; 10 к/10 к	SOT23,SOD23	B·E·C
EGs	BCW66G	SIEM	non	V _{CBD} =75B; I _C =800 мА; P _D =330 мВт; h ₂₁ =160400; f _T =170 МГц	SOT23,SOD23	B-E-C
EH	1SS365	SANYO	di	V _B <10B; I _E <35 mA; V _E (I _E =10 mA)<0.58B; I _B <10 mkA	SOT23,SOD23	A·n.c·K
EH	BCW66H	CDIL	non	V _{CRD} =75B; I _C =800 мА; P _D =330 мВт; h ₂₁ =250630; f _T >100МГц	SOT23.SOD23	B-E-C
EH	BCW66H	ZETEX	non	V _{GB0} =75B; I _C =800мA; P _D =330мBт; h ₂₁ =250630; f _T >100МГц	SOT23.SOD23	B·E·C
EH	MMBZ4716	VISH	dz	V ₂ (I ₂₇ =50 mKA)=37.141.0 B; I _B <0.01 mKA	SOT23.SOD23	A·n.c.·K
FHAA	MAX6326UR22	MAX	mrc	V _{TB} =2.2B; V _{DD} =1.25.5B; I _{CC} <1.75mkA	SOT23,SOD23	
EHs	BCW66H	SIEM	non	V _{CRD} =75 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =250630; f _T >170 МГц	SOT23.SOD23	- 00
EIAA	MAX6327UP22	MAX	mrc	V _{TB} =2.2B; V _{DD} =1.25.5B; I _{DE} <1.75mxA	SOT23,SOD23	
EJ	MMBZ4717	VISH	dz	V _X (I ₇₇ =50 mkA)=40.945.2 B; I _R <0.01 mkA	SOT23,SOD23	
	MAX6328UR22	MAX	mrc	V _{TR} =2.2B; V _{DR} =1.25.5B; I _{DE} <1.75mKÅ	SOT23,SOD23	
EK	BCX41	ZETEX	non	V_{CB0} =125B; I_C =800 MA; P_D =330 MBT; h_{P1} >63; f_T >100 MFu	SOT23,30D23	
	MAX6330LUR	MAX	ubu	V _{TC} =4.63 B; V _C =5.0B; I _C =5.0 MA	SOT23,SOD23	57251508
LIVE			mrc			SHUNT
EKs	BCX41	SIEM	npn	V_{CB0} =125B; I_C =800 MA; P_D =330 MBT; h_{21} >63; f_T =100 M Γ_{II}	SOT23,SOD23	
ELAA	MAX6331LUR	MAX	rea+	V _{IR} =4.63B; V _{OLIT} =5.0B; I _{OLIT} >50 MA	SOT23,SOD23	GND · RST ·

SOT490 TESM VMT3 1 SOT523 SOT323 SOT23-3 1 SOT523 SOT324 SOD23-3 1 SOT523 SOT346 SOD23-3 1 SOT523 SOT523 SOT525 SO

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
EMAA	MAX6330TUR	MAX	reg+ mrc	V _{TR} =3.06B; V _{OUT} =3.3B; I _{OUT} >50 мA	SOT23,SOD23	GND · RST · SHUNT
EN	2SK3288	REN	nMOS	V _{DS} =30 B; I _D =100 mA; P _D =400 mBT; R _{DS(on)} <7 Om	SOT23,SOD23	G·S·D
EN	2SK3378	REN	nMOS	V _{DS} =30 B; I _D =100 mA; P _D =300 mBT; R _{DS(on)} <7 Om	SOT323,SC70	G·S·D
ENAA	MAX6331TUR	MAX	reg+ mrc	V _{TR} =3.06B; V _{OUT} =3.3B; I _{OUT} >50 MA	SOT23,SOD23	GND·RST· SHUNT
EO	KTC3265	KEC	npn	V_{C80} =35B; I_C =800 mA; P_D =200 mBt; h_{21} =100200; f_T >120 M Γ_{II}	SOT23,SOD23	B-E-C
EPAA	MAX6331SUR	MAX	reg+ mrc	V _{TR} =2.78B; V _{OUT} =3.0B; I _{OUT} >50 MA	SOT23,SOD23	GND·RST· SHUNT
ET	BCW65AR	SIEM	npn	V_{CB0} =60 B; I_C =800 mA; P_0 =330 mBr; h_{21} =100250; f_T =170 M Γ_{II}	SOT23,SOD23	C·B·E
EU	BCW65BR	SIEM	npn	V_{C80} =60 B; I_C =800 mA; P_D =330 mBt; h_{21} =160400; f_T =170 M Γ_{II}	SOT23,SOD23	C·B·E
EW	BCW65CR	SIEM	npn	V_{C80} =32 B; I_C =800 мA; h_{21} >240; f_1 >100 МГц	SOT23,SOD23	C·B·E
EWAA	MAX6326UR23	MAX	mrc	V _{TR} =2.32B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA	SOT23,SOD23	GND · RST · V _{GC}
EX	BCW65FR	SIEM	npn	V_{CB0} =45B; I_C =800 MA; h_{21} >100; f_T >100 MFu	SOT23,SOD23	C-B-E
EXAA	MAX6326UR24	MAX	mrc	V _{TR} =2.4B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA	SOT23,SOD23	GND · RST · V _{CC}
EY	BCW65GR	SIEM	npn	V_{C80} =45 B; I_C =800 mA; h_{21} >160; f_T >100 MF $_{\rm LL}$	SOT23,SOD23	C·B·E
EY	KTC3265	KEC	npn	V _{CB0} =35 B; I _C =800 мА; P _D =200 мВт; h ₂₁ =160320; f _T >120 МГц	SOT23,SOD23	B-E-C
EYAA	MAX6326UR25	MAX	mrc	V _{TB} =2.5B; V _{DD} =1.25.5B; I _{DG} <1.75 мкA	SOT23,SOD23	GND · RST · V _{CC}
EZ	BCW65HR	SIEM	non	V_{C80} =45B; I_C =800 MA; h_{21} >240; f_T >100 MF μ	SOT23,SOD23	C·B·E
EZAA	MAX6326UR26	MAX	mrc	V _{TR} =2.63B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA	SOT23,SOD23	GND · RST · Voc
F	IRLML6401	IR	oMOS	HEXFET; V _{DS} =12 B; I _D =3.4A; P _D =1.3 BT; R _{DS(on)} <0.125 Om	SOT23,SOD23	
F	MRF927T1	MOT	ngn	V _{CBO} =20B; I _C =10 MA; P _D =100 MBT; h ₂₁ =50200; f _T =8 FFu	SOT323,SC70	
F0	HSMP3820	HP	pin	I _F <1 A; V _{BB} >50 B; R _S <0.6 Om; C _D <0.8 nΦ	SOT23,SOD23	(SOUNDED
F02	DTD123TK	ROHM	Dnpn	N _{C80} = 50 B; I _C = 500 MA; P _D = 200 MBT; h ₂₁ = 100600; f _T > 200 MFu; R ₁ = 2.2 KOM	SOT346,SC59	
F03	DTB143TK	ROHM	Dpnp	V_{C80}^{-} 50 B; I_{C}^{-} 500 xA; P_{D}^{-} 200 xBr; h_{21}^{-} 100600; f_{T}^{-} 200 MFu; R_{s}^{-} 4.7 xGm	SOT346,SC59	B-E-C
F04	DTD114TK	ROHM	Dnpn	V _{гва} = 50 B; I _с = 500 мA; P _п = 200 мВт; h ₂₄ = 100600; f _T > 200 МГц; R ₁ = 10 кОм	SOT346,SC59	B-E-C
F07	DTD163TK	ROHM	Dnon	V _{CBB} =50B; I _C =500 мA; P _D =200 мВт; h ₂₁ =100600; f _T >200 МГц	SOT346,SC59	
F1	HSMP3821	HP	oin	I _E <1A; V _{BB} >50B; R _S <0.60м; С _D <0.8пФ	SOT23.SOD23	
F1	KST1009F1	SAMS	npn	V _{CR0} =50B; I _C =50 mA; P _D =350 mBT; h ₂₁ =3060; f _T >150 MFu	SOT23.SOD23	B•E•C
Fí	MMBC1009F1	MOT	npn	V _{DB0} =50 B; I _C =50 мA; P _D =300 мВт; h ₂₁ =3060	SOT23.SOD23	B·E·C
F1	MMBZ5236BT	DIODS	dz	V ₂ (I _{2T} =20 mA)=7.137.88B; I _B <3 mKA	SOT523	A·n.c.·K
F11	DTB113EK	ROHM	Dono	V _{CR0} =50 B; I _C =500 MA; P _D =200 MBT; h ₂₁ >33; f _T >200 MFu; R ₁ /R ₂ =1/1 KOM	SOT346.SC59	10.000000000000000000000000000000000000
F12	DTB123EK	ROHM	Dpnp	V _{CB0} = 50 B; I _C = 500 MA; P _D = 200 MBT; h ₂₁ > 39; f _T > 200 MFu; R ₁ /R ₅ = 2/2 2 xOm	SOT346,SC59	TUE 5.
F13	DTB143EC	ROHM	Dpnp	V _{C80} =50B; I _C =500 мA; P _D =200 мBт; h ₂₁ >47; f _T >200 MΓц; R ₁ /R ₉ =4.7/4.7 κOm	SOT23,SOD23	B-E-C
F13	DTB143EK	ROHM	Dpnp	V_{C80} :50 B; I_C :500 xA; P_D :200 xBT; h_{21} >47; f_T >200 MFu; I_T :70 XFu; I_T :70 XFu;	SOT346,SC59	B-E-C
F14	DTB114EK	ROHM	Dono	V _{CBB} =50B; I _C =500 MA; P _B =200 MBT; h ₂₁ >56; f _T >200 MFu; R ₁ /R ₂ =10/10 KOM	SOT346.SC59	B-E-C
F10	KSA1182	SAMS	ono	V _{гэл} ; 35B; I _с = 500 мА; Р _п = 150 мВт; h ₂₁ = 70140; f _T > 200 МГц	SOT23.SOD23	
F1p	BFS18	PHIL	non	V ₀₈₀ =30 B; I _C =30 мA; P _D =250 мВт; h ₂₁ =35125; f _T =200 МГц	SOT23.SOD23	CCC A 74-000
F1Y	KSA1182	SAMS	ono	V _{CB0} =35 B; I _C =500 mA; P _D =150 mBr; h ₂₁ =120240; f _T >200 MFu	SOT23,SOD23	
F2	BES19	SGS	nan	V _{CR0} =30 В; I _C =30 мА; P _D =250 мВт; h ₂₁ =65225; f _T =260 МГц	SOT23,SOD23	1000 00
F2	HSMP3822	HP	oin×2	I _F <1A; V _{RR} >50B; R _S <0.60м; С _П <0.8пФ	SOT23,SOD23	
F2	KST1009F2	SAMS	non	V _{C80} =50B; I _C =50MA; P _D =350 MBT; h ₂₁ =4080; f _T >150 MFu	SOT23,30D23	
F2	MMBZ5237BT		, ,			
		DIODS	dz	V _Z (I _{ZT} =20 MA)=7.798.61 B; I _R <3 MKA	SOT523	A·n.c.·K
F21	DTD113EK	ROHM	Dnpn	V _{C80} =50 B; I _C =500 MA; P _D =200 MBr; h ₂₁ >33; f ₇ >200 MFu; R ₁ /R ₂ =1/1 κOm	SOT346,SC59	
F22	DTD123EK	ROHM	Dnpn	V_{C80} : 50 B; I_C : 500 MA; P_D : 200 MBr; h_{21} > 39, f_T > 200 MFu; R_1/R_2 : 2.2/2.2 KOM	SOT346,SC59	
F23	DTD143EC	ROHM	Dnpn	V_{C80} =50 B; I_{C} =500 MA; P_{D} =200 MBr; h_{21} >47; f_{T} >200 MFu; R_{1}/R_{2} =4.7/4.7 kOM	SOT23,SOD23	100es W
F23	DTD143EK	ROHM	Dnpn	V_{C80} =50 B; I_C =500 xA; P_D =200 xBT; h_{21} >47; f_T >200 MFu; P_1/P_D =4.7/4.7 kOm	SOT346,SC59	B-E-C





Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3
F23	DTD143ES	ROHM	Dnpn	V_{CB0} =50 B; $I_{\rm C}$ =500 MA; $P_{\rm D}$ =200 MBT; h_{21} >47; $f_{\rm T}$ >200 MFu; $R_{\rm L}/R_{\rm Z}$ =4.7/4.7 kOm	S0T23,S0D23	B·E·C
F23	DTD143TK	ROHM	Dnpn	V_{CB0} =50 B, I_{C} =500 MA; P_{D} =200 MBT; h_{21} =100600; f_{T} >200 MFu; R_{1} =4.7 kOM	SOT346,SC59	B·E·C
F24	DTD114EK	ROHM	Dnpn	V_{CB0} =50 B; I_C =500 mA; P_D =200 mBr; h_{21} >56; f_T >200 M Γ_{II} ; R_1/R_2 =10/10 кОм	SOT346,SC59	B·E·C
F2p	BFS19	PHIL	npn	V _{CB0} =30 B; I _C =30 мA; P _D =250 мВт; h ₂₁ =65225; f _T =260 МГц	SOT23,SOD23	B·E·C
F2t	BFS19	PHIL	npn	V _{CB0} =30 B; I _C =30 мA; P _D =250 мВт; h ₂₁ =65225; f _T =260 МГц	SOT23,SOD23	B·E·C
F3	1SS193	TOSH	di	V _R <80B; I _F <100 mA; V _F (I _F =100 mA)<1.2 B; I _R <0.5 mrA; t _{RR} <4 hc	SOT346,SC59	A•n.c.•K
F3	2SC4399	SANYO	npn	V _{CB0} =30 B; I _C =30 mA; P _D =150 mBT; h ₂₁ =60120; f _T >320 MFu	SOT323,SC70	B·E·C
F3	HSMP3823	HP	pin×2	I _F <1A; V _{BR} >50B; R _S <0.6Ом; С ₀ <0.8пФ	SOT23,SOD23	K1-K2-A1,A2
F3	KST1009F3	SAMS	npn	V _{CB0} =50 B; I _C =50 мА; P _D =350 мВт; h ₂₁ =60120; f _T > 150 МГц	SOT23,SOD23	B·E·C
F3	MMBC1009F3	MOT	npn	V _{CB0} =50 B; I _C =50 мА; P _D =300 мВт; h ₂₁ =60120	SOT23,SOD23	B·E·C
F4	2SC4399	SANYO	non	V _{CB0} =30 B; I _C =30 мA; P _D =150 мВт; h ₂₁ =90180; f _T >320 МГц	SOT323,SC70	B·E·C
F4	BFS18R	PHIL	npn	V _{CB0} =20 B; I _C =30 мA; P _D =110 мВт; h ₂₁ =35; f _T =200 МГц	SOT23,SOD23	E·B·C
F4	HSMP3824	HP	pin×2	I _E <1A; V _{BR} >50B; R _S <0.60м; С ₀ <0.8пФ	SOT23,SOD23	A1+A2+K1,K2
F4	KST1009F4	SAMS	npn	V _{CB0} =50 B; I _C =50 мА; P ₀ =350 мВт; h ₂₁ =90180; f _T >150 МГц	SOT23, SOD23	B·E·C
F4	MMBZ5239BT	DIODS	dz	V ₂ (I ₂₇ =20 mA)=8.659.56 B; I _R <3 mkA	SOT523	A+n.c.+K
F5	1SS250	TOSH	di	V _B <200 B; I _E <100 mA; V _E (I _E =100 mA)<1.2 B; I _B <1.0 mKA; t _{BB} <60 HC	SOT346,SC59	A·n.c.·K
F5	1SS370	TOSH	di	V _B < 200 B; I _E < 100 mA; V _E (I _E = 100 mA)< 1.2 B; t _{BB} < 60 Hc	SOT323,SC70	A·n.c.·K
F5	2SC4399	SANYO	non	V _{cno} =30B; I _c =30mA; P _n =150mBT; h ₂₁ =135270; f _T >320MFu	SOT323,SC70	B·E·C
F5	BFS19R	PHIL	non	V _{GBO} =20 B; I _G =30 mA; P _D =200 mBT; h ₂₁ =225; f _T =260 MFц	SOT23.SOD23	E·B·C
F5	KST1009F5	SAMS	non	V _{CR0} =50 B; I _C =50 MA; P _D =350 MBT; h ₂₁ =135270; f _T >150 MFц	SOT23.SOD23	B·E·C
F5	MMBZ5240BT	DIODS	dz	V _Z (I _{ZT} =20 mA)=9.510.5 B; I _B <3 mkA	SOT523	A·n.c.·K
F52	DTB123YC	ROHM	Dpnp	V_{CB0} =50B; I_C =500 MA; P_D =200 MBT; h_{21} =100600; f_T >200 MFu; P_1 =2.2 kOM	SOT23,SOD23	B·E·C
F52	DTB123YK	ROHM	Dpnip	V_{C80} =50 B; I_{c} =500 mA; P_{D} =200 mB τ ; h_{21} >56; f_{T} >200 M Γ u; R_{1}/R_{2} =2.2/10 kOm	SOT346,SC59	B·E·C
F62	DTD123YK	ROHM	Dnpn	V_{CB0} =50 B, $I_{\rm C}$ =500 MA; $P_{\rm D}$ =200 MB τ ; $h_{21}>$ 56; $f_{\rm T}>$ 200 M Γ u; $R_{\rm 1}/R_{\rm 2}$ =2.2/10 kOM	SOT346,SC59	B·E·C
F7	BAV99RWT1	ON	di×2	V _R <70B; I _F <215 mA; V _F (I _F =150 mA)<1.25 B; I _R <2 mkA; t _{RR} <4 Hc	SOT323,SC70	A1 · K1,A2 · K2
F8	BF824W	PHIL	pnp	V_{CB0} =30 B; I_C =25 mA; P_D =200 mBT; h_{21} >25; f_T >400 MFu	SOT323,SC70	B·E·C
F8p	BF824	PHIL	pnp	V _{CB0} =30 B; I _C =25 mA; P _D =250 mBT; f _T =450	SOT23,SOD23	B·E·C
F8t	BF824	PHIL	pnp	V _{CB0} =30 B; I _C =25 mA; P _D =250 mBT; f _T =450	SOT23,SOD23	B·E·C
F9	1SS321	TOSH	shd×2	V _R >10B; V _E (I _F =50mA)<1.0B; I _E (V _R =10B)<0.5mkA; C _T <4.5nΦ	SOT346,SC59	A1+A2+K1,K2
F9	2SA1774	ON	pnp	V _{CB0} =60 B; I _C = 100 мА, P _D = 150 мВт; h ₂₁ = 120560; f _T = 140 МГц	SOT416,SC75A	B·E·C
F92	DTB123TK	ROHM	Dpnp	V_{CB0} =50 B, $I_{\rm C}$ =500 MA; $P_{\rm D}$ =200 MBT; h_{24} =100600; $f_{\rm T}$ >200 MFu; $R_{\rm 1}$ = 2.2 kOm	SOT346,SC59	B·E·C
F93	DTB143TK	ROHM	Dpnp	V_{C80} =50 B; $I_{\rm C}$ =500 мA; $P_{\rm D}$ =200 мВт; $h_{\rm 21}$ >100600; $f_{\rm 7}$ >200 МГц; $R_{\rm 1}$ =4.7 кОм	SOT346,SC59	B-E-C
FA	2SC5851A	REN	non	V _{CB0} =30 B; I _C =100 мА; P _D =150 мВт; h ₂₁ =3575; f _T =230 МГц	SOT323,SC70	B·E·C
FA	HSMP4820	HP	pin	$I_F \le 1 \text{A}; P_D \le 250 \text{ MBT}; V_{BR} \ge 50 \text{ B}; R_S \le 0.6 \text{ OM}; C_D \le 1.0 \text{ m}\Phi; L_T = 1.0 \text{ MF}$	SOT23,SOD23	A·A·K
FAAA	MAX6326UR27	MAX	mrc	V _{IR} =2.7B; V _{DD} =1.25.5B; I _{DC} <1.75mkA	SOT23,SOD23	GND · RST · V _C
FB	2SC5851B	REN	npn	V _{CB0} =30 B; I _C =100 mA; P _D =150 mBT; h ₂₁ =60120; f _T =230 MFu	SOT323,SC70	B·E·C
FBAA	MAX6326UR28	MAX	mrc	V _{TR} =2.8B; V _{DD} =1.25.5B; I _{CC} <1.75mkA	SOT23,SOD23	GND-RST-V _C
FC	2SC5851C	REN	npn	V _{CB0} =30 B; I _C =100 мA; P _D =150 мВт; h ₂₁ =100200; f _T =230 МГц	SOT323,SC70	B·E·C
FCAA	MAX6326UR29	MAX	mrc	V _{TR} =2.93B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA	SOT23,SOD23	GND · RST · V _C
FD	BCV26	SGS	dpnp	V _{CB0} =40 B; I _C =500 mA; P _D =360 mBT; h ₂₁ > 10000; f _T =200 MFц	SOT23,SOD23	B.E.C
FDAA	MAX6326UR31	MAX	mrc	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{CC} <1.75 mcA	SOT23,SOD23	GND-RST-V _C
FDp	BCV26	PHIL	dpnp	V _{CBD} =40 B; I _C =300 mA; P _D =250 mBT; h ₂₁ > 20000; f _T =220 MFц	SOT23,SOD23	2/20/20/20/20/20/20/20/20/20/20/20/20/20
FDs	BCV26	INF	dpnp	V _{CB0} =40 B; I _C =500 mA; P _D =360 mBT; h ₂₁ > 10000; f _T =200 MFц	SOT23,SOD23	B·E·C
FDt	BCV26	PHIL	dpnp	V _{CR0} =40 B; I _C =300 mA; P _D =250 mBT; h ₂₁ > 20000; f _T =220 MFu,	SOT23,SOD23	10 00 00
FE	BCV46	SGS	dono	V _{CPD} =80 B; I _C =500 мA; P _D =330 мВт; h ₂₁ >400; f _T >200 МГц	SOT23,SOD23	
	MAX6326UR30	MAX	mrc	V _{TB} =3.0B; V _{DD} =1.25.5B; I _{DC} <1.75mκA	SOT23,SOD23	

SOT490 TESM VMT3 1 SOT523 SOT323 SOT23-3 1 SOT523 SOT324 SOD23-3 1 SOT523 SOT346 SOD23-3 1 SOT523 SOT523 SOT525 SO

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
Ep	BCV46	PHIL	dpnjo	V _{G80} =80 B; I _G =500 mA; P _D =250 mBr; h ₂₁ >4000; f _T =220 MFu,	SOT23,SOD23	B·E·C
Es	BCV46	INF	dpnp	V _{C80} =80 B; I _C =500 мА; P _D =360 мВт; h ₂₁ >4000; f _T =200 МГц	SOT23,SOD23	B·E·C
Et	BCV46	PHIL	dpnjo	V ₀₈₀ =80 B; I ₀ =500 мA; P ₀ =250 мВт; h ₂₁ >4000; f ₁ =220 МГц	SOT23,SOD23	B·E·C
FF	BCV27	SGS	dnpn	V _{CR0} =40 B; I _C =500 MA; P _D =330 MBT; h ₂₁ >100; f _T >170 MTu,	SOT23,SOD23	B·E·C
FF	JDV3C11	TOSH	var×2	V _B <20B; I _B <0.01 mKA; C _{1B} =65.874.2 пФ; C _{4.5.B} =11.514.3	SOT23,SOD23	A1-A2-K1,K2
FFAA	MAX6327UR23	MAX	mrc	V _{TB} =2.32B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	GND · RST · V _{cr}
FFMA	MAX6327UR31	MAX	mrc	V _{TB} =3.08B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	GND · RST · V _{cr}
FFNA	MAX6327UR30	MAX	mrc	V _{TB} =3.0B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA	SOT23,SOD23	
FFp	BCV27	PHIL	dnpn	V _{G80} =40 B; I _C =300 mA; P _D =250 mBr; h ₂₁ > 20000; f _T =220 MFu	SOT23,SOD23	
FFs	BCV27	INF	dnon	V_{C80} =40 B; I_C =500 mA; P_D =360 mBr; h_{21} >10000; f_T =170 MFu	SOT23,SOD23	B·E·C
FFt	BCV27	PHIL	dnpn	V _{C80} =40 B; I _C =300 MA; P _D =250 MBT; h ₂₁ > 20000; f _T =220 MFu	SOT23,SOD23	
FG	BRC114ECM	REN	Dnon	V _{CC} =50B; I _{OUT} =100 mA; P _D =150 mBT; h ₂₁ >30; 10 к/10 к	SOT323.SC70	
FG	BRC114EMP	REN	Dnpn	V _{DC} =50B; I _{DUT} =100 mA; P _D =150 mB;; h ₂₁ >30; 10 к/10 к	SOT23,SOD23	120000000000000000000000000000000000000
550.65	MAX6327UR24	MAX	mrc	V _{TR} =2.4B; V _{DD} =1.25.5B; I _{DD} <1.75 mKA	SOT23,SOD23	
FGo	BCV47	PHIL	dnpn	V ₀₈₀ =80 B; I ₀ =500 MA; P ₀ =250 MBr; h ₂₁ >4000; f ₇ =220 MFu	SOT23,SOD23	
FGs	BCV47	INF	dnpn	V _{G80} =80 B; I _C =500 mA; P _D =360 mBr; h ₂₁ >4000; f _T =170 MFu,	SOT23,SOD23	
FGt	BCV47	PHIL	dnpn	V _{CB0} =80 B; I _C =500 мА; Р _D =300 мВг; I ₁₂ =24000; I ₇ =770 МГц	SOT23,SOD23	
FH	1SS366	SANYO	shd×2	V _B >10B; V _E (I _E =10MA)<0.58B; I _E (V _B =10B)<10MKA	SOT23,SOD23	
FH	1SS375		shd×2	V _B >10B; V _E (I _E =10MA)<0.58B; I _B (V _B =10B)<10MKA	SOT323,SC70	
	MAX6327UR25	MAX	mrc	V _{TB} =2.5B;V _{DD} =1.25.5B; I _{CC} <1.75 m/A	SOT23,SOD23	
FHs	BFN24	SIEM			SOT23,SOD23	
FIAA	MAX6327UR26	MAX	npn	V _{CBO} =250 B; I _C =200 мА; P _O =360 мВт; h ₂₁ >40; f _T =70 МГц	SOT23,SOD23	
FJAA	MAX6327UH26 MAX6327UR27	MAX	mrc mrc	V _{TR} -2.63B; V _{DD} -1.25.5B; I _{CC} <1.75 m/A		
FJS	BFN26	SIEM	_	V _{TR} -2.7B; V _{DD} -1.25.5B; I _{CC} <1.75 mcA	SOT23,SOD23	- 01
FKAA			npn	V _{C80} =300 B; I _C =200 мА; P _D =360 мВт; h ₂₁ >30; f _T =70 МГц	SOT23,SOD23	
	MAX6327UR28	MAX	mrc	V _{TR} =2.8B; V _{DD} =1.25.5B; I _{CC} <1.75 mKA	SOT23,SOD23	
FKs	BFN25	SIEM	pnp	V _{CB0} =250 B; I _C =200 MA; P _D =360 MBT; h ₂₁ >40; f _T =100 MΓц	SOT23,SOD23	
FLAA	MAX6327UR29	MAX	mrc	V _{TR} =2.93B; V _{DD} =1.25.5B; I _{CC} <1.75 mxA	SOT23,SOD23	
FLs	BFN27	SIEM	pnp	V _{C80} =300 B; I _C =200 мА; P _D =360 мВт; h ₂₁ >30; f _T =100 МГц	SOT23,SOD23	
F0	2SC2716O	TOSH	npn	V _{CE0} =35B; I _C =100 мA; P _D =150 мBт; h ₂₁ =70140; f _T >80 МГц	SOT23,SOD23	
	MAX6328UR23	MAX	mrc	V _{TR} =2.32B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA	SOT23,SOD23	
FPAA	MAX6328UR24	MAX	mrc	V _{TR} =2.4B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA	SOT23,SOD23	
FQ	2SA1037AKQ	ROHM	pnp	V_{C80} =50 B; I_C =150 MA; P_D =200 MBT; h_{21} =120270; f_T >140 MF $_{L}$	SOT346,SC59	
FQ	2SA1576AQ	ROHM	pnp	V _{GB0} =50 B; I _C =150 мА; P _D =200 мВт; h ₂₁ =120270; f _T >140 МГц	SOT323,SC70	
FQ	2SA1774	ROHM	pnp	V_{C80} =60 B; I_C =150 mA; P_D =200 mBr; h_{21} =120270; f_T >140 M Γ_{II}	SOT416,SC75A	
FQ	2SA2029Q	ROHM	pnp	V_{C80} =60 B; I_C =150 mA; P_D =150 mBr; h_{21} =120270; f_T >140 MFu	VMT3,VMD3	B·E·C
F-Q	2PA1576Q	PHIL	pnp	V _{CE0} =50B; I _C =100 мA; P ₀ =200 мВт; h ₂₁ =120270; f _T =100 МГц	SOT323,SC70	SA PARKS THE
	MAX6328UR25	MAX	mrc	V _{TR} =2.5B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	- 04
FR	2SA1034R	PAN	pnp	V _{C80} =35B; I _C =100 мA; P _D =200 мВт; h ₂₁ =180360; f ₁ =200 МГц	SOT23,SOD23	0.0000000000000000000000000000000000000
FR	2SA1037AKR	ROHM	pnp	V_{C80} =50 B; I_C =150 mA; P_0 =200 mBr; h_{21} =180390; f_T >140 M Γ_{LL}	SOT346,SC59	B·E·C
FR	2SA1531R	PAN	pnp	V _{C80} =35 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =180360; f _T =80 МГц	SOT323,SC70	B·E·C
FR	2SA1576AR	ROHM	pnp	V _{CB0} =50 B; I _C =150 мA; P _D =200 мВт; h ₂₁ =180390; f _T >140 МГц	SOT323,SC70	B·E·C
FR	2SA1774	ROHM	pnp	V _{G80} =60 B; I _C =150 мA; P _D =200 мВт; h ₂₁ =180390; f _T >140 МГц	S0T416,SC75A	B·E·C
FR	2SA2029R	ROHM	pnp	V _{C80} =60 B; I _C =150 мA; P _D =150 мBт; h ₂₁ =180390; f _T >140 МГц	VMT3,VMD3	B·E·C
FR	2SC2716R	TOSH	npn	V _{CE0} =35B; I _C =100 мA; P ₀ =150 мВт; h ₂₁ =4080; f _T >80 МГц	SOT23,SOD23	B.E.C
F-R	2PA1576R	PHIL	pnp	V_{GE0} =50 B; I_C =100 MA; P_D =200 MBT; h_{21} =180390; f_T >100 MFu	SOT323,SC70	B·E·C
FRAA	MAX6328UR26	MAX	mrc	V _{TR} =2.63B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA	SOT23,SOD23	GND · RST · V _{CC}
FS	2SA1034S	PAN	pnp	V _{C80} =35 B; I _C =100 мA; P _D =200 мВт; h ₂₁ =260520; f _T =200 МГц	SOT23,SOD23	B-E-C
FS	2SA1037AKS	ROHM	pnp	V _{G80} =50 B; I _C =150 MA; P _D =200 MBT; h ₂₁ =270560; f _T >140 MFu	SOT346,SC59	B·E·C
FS	2SA1531S	PAN	pnp	V _{сво} =35B; I _C =50мA; P _D =150мВт; h ₂₁ =260520; f _T =80МГц	SOT323,SC70	B·E·C
FS	2SA1576AS	ROHM	pnp	V ₀₈₀ =50 B; I _C =150 мА; P _D =200 мВт; h ₂₁ =270560; f _T >140 МГц	SOT323,SC70	
FS	2SA1774	ROHM	ono	V _{G80} =60 B; I _C =150 мА; Р _D =200 мВт; h ₂₁ =270560; f _T >140 МГц	SOT416,SC75A	-0.011.02
FS	2SA2029S	ROHM	pnp	V _{CR0} =60 B; I _C =150 MA; P _D =150 MBr; h ₂₁ =270560; f _T >140 MF _U		B·E·C





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
F-S	2PA1576S	PHIL	pnp	V _{CEO} =50 B; I _C =100 мA; P _D =200 мВт; h ₂₁ =270560; f _T >100 МГц	S0T323,SC70	B·E·C
FS-	2SC5890	REN	npn	V _{CB0} =20B; I _C =75мA; P _D =700мBт; h ₂₁ =100200; f _T >5.5ГГц	SOT23,SOD23	B-E-C
FSAA	MAX6328UR27	MAX	mrc	V _{TB} =2.7B; V _{DD} =1.25.5B; I _{DD} <1.75mkA	SOT23,SOD23	GND · RST · V _{CC}
FT	2SA1034T	PAN	pnp	V _{CR0} =35B; I _C =100 MA; P _D =200 MBT; h ₂₁ =360700; f _T =200 MFu	SOT23,SOD23	B·E·C
FT	2SA1531T	PAN	pnp	V _{CR0} =35B; I _C =50 мА; P _D =150 мВт; h ₂₁ =360700; f ₁ =80 МГц	SOT323,SC70	B·E·C
FTAA	MAX6328UR28	MAX	mrc	V _{TB} =2.8B; V _{DD} =1.25.5B; l _{DC} <1.75mkA	S0T23,S0D23	GND · RST · V _{CC}
FtQ	2PA1576Q	PHIL	pnp	V _{Cm} =50 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =120270; f _T =100 МГц	S0T323,SC70	
FtR	2PA1576R	PHIL	pnp	V _{CFD} =50 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =180390; f _T >100 МГц	S0T323,SC70	B-E-C
FtS	2PA1576S	PHIL	onp	V _{CED} =50 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =270560; f _T >100 МГц	S0T323.SC70	
FUAA	MAX6328UR29	MAX	mrc	V _{тв} =2.93B; V _{пп} =1.25.5B; I _{пп} < 1.75 мкА		GND · RST · V _{CC}
FV	1SV248	SANYO	pin	V _B >50B; I _E <50 mA; V _E (I _E =50 mA)=0.92B; I _B <0.1 mkA	S0T323,SC70	
FV	1SV250	SANYO	pin	V _B >50B; I _E <50 mA; V _E (I _E =50 mA)=0.92B; I _B <0.1 mkA	SOT23,SOD23	1911
FVAA	MAX6328UR31	MAX	mrc	V _{IR} =3.08B; V ₀₀ =1.25.5B; I _{CC} <1.75 mKA		GND · RST · V _{CC}
	MAX6328UR30	MAX	mrc	V _{TR} =3.0B; V _{DD} =1.25.5 B; I _{DC} <1.75mKA		GND RST VCC
FY	2SC2716Y	TOSH	non	V _{CB} =35 B; I _C =100 MA; P _D =150 MBT; h ₂₁ =120240; f _T >80 MFu	SOT23,SOD23	
FZAP	MAX6012AEUR	MAX	vref	V _{IN} =2.512.6B; TC _{VOIII} < 20 ppm / C; V _{OIII} = 1.247 B	SOT23,SOD23	
		_				
	MAX6025AEUR	MAX	vref	V _{IN} =V _{OUT} + 0.212.6B; TC _{VOUT} < 20 ppm/°C; V _{OUT} = 2.500 B	SOT23,SOD23	
	MAX6041AEUR	MAX	vref	V _{IN} =V _{OUT} + 0.212.6 B; TC _{VOUT} < 20 ppm/°C; V _{OUT} = 4.096 B	SOT23,SOD23	100000000000000000000000000000000000000
	MAX6045AEUR	MAX	vref	V _{IN} =V _{OUT} +0.212.6B; ΤC _{VOUT} <20 ppm/°C; V _{OUT} =4.500B	S0T23,S0D23	100000000000000000000000000000000000000
FZAT	MAX6050AEUR	MAX	vref	V _{IN} =V _{OUT} +0.212.6B; TC _{VOUT} <20 ppm/°C; V _{OUT} =5.000B	SOT23,SOD23	
	MAX6021AEUR	MAX	vref	V _{IN} =2.512.6B; TC _{VOUT} < 20 ppm/°C; V _{DUT} =2.048B	SOT23,SOD23	
FZAV	MAX6346UR33	MAX	mrc	V _{TR} =3.3B; V _{DD} =1.25.5B; I _{DC} <1.75mkA	S0T23,S0D23	
	MAX6346UR34	MAX	mrc	V _{TR} =3.4 B; V _{DD} =1.25.5 B; I _{DD} <1.75 MKA		GND-RST-V _{CC}
FZAX	MAX6346UR35	MAX	mrc	V _{TR} =3.5B; V _{DD} =1.25.5B; I _{CC} <1.75mkÅ		GND · RST · V _{CC}
FZAY	MAX6346UR36	MAX	mrc	V _{TR} =3.6B; V _{DD} =1.25.5B; I _{DC} <1.75mkA	SOT23,SOD23	GND+RST+V _{CC}
FZAZ	MAX6346UR37	MAX	mrc	V _{TR} =3.7B; V _{DD} =1.25.5B; I _{CD} <1.75mkA		GND · RST · V _{CC}
FZBA	MAX6346UR38	MAX	mrc	V _{TR} =3.8B; V _{DD} =1.25.5B; I _{DC} <1.75mkA	SOT23,SOD23	GND · RST · V _{CC}
FZBB	MAX6346UR39	MAX	mrc	V _{TR} =3.9B; V _{DD} =1.25.5 B; I _{CC} <1.75мкА	SOT23,SOD23	GND · RST · V _{CC}
FZBC	MAX6346UR40	MAX	mrc	V _{TR} =4.0B; V _{DD} =1.25.5B; I _{CC} <1.75mkA	SOT23,SOD23	GND · RST · V _{CC}
FZBD	MAX6346UR41	MAX	mrc	V _{TR} =4.1B; V _{DD} =1.25.5B; I _{CC} <1.75mkA	SOT23,SOD23	GND · RST · V _{CC}
FZBE	MAX6346UR42	MAX	mrc	V _{IR} =4.2B; V _{DD} =1.25.5 B; I _{CC} <1.75мкА	SOT23,SOD23	GND-RST-V _{CC}
FZBF	MAX6346UR43	MAX	mrc	V _{TR} =4.3B; V _{DD} =1.25.5B; I _{DD} <1.75MKÅ		GND · RST · V _{CC}
FZBG	MAX6346UR44	MAX	mrc	V _{TB} =4.38B; V _{DD} =1.25.5B; I _{DG} <1.75 мкA		GND-RST-V _{CC}
	MAX6346UR45	MAX	mrc	V _{TB} =4.5B; V _{DD} =1.25.5B; I _{CC} <1.75mkA		GND · RST · V _{CC}
	MAX6346UR46	MAX	mrc	V _{TB} =4.63B; V _{DD} =1.25.5B; I _{DC} <1.75 mKA		GND · RST · V _{CC}
	MAX6347UR33	MAX	mrc	V _{TR} =3.3B; V _{DD} =1.25.5B; I _{GC} <1.75mκA		GND · RST · V _{CC}
	MAX6347UR34	MAX	mrc	V _{TB} =3.4B; V _{DD} =1.25.5B; I _{CC} <1.75mkA		GND · RST · V _{CC}
	MAX6347UR35	MAX	mrc	V _{IR} =3.5B; V _{OD} =1.25.5B; I _{OC} <1.75мкА		GND · RST · V _{CC}
	MAX6347UR36	MAX	mrc	V _{IR} =3.6B; V _{DD} =1.25.5B; I _{DC} <1.75мкА		GND · RST · VCC
	MAX6347UR37	MAX	mrc	V _{TR} -3.7B; V _{DD} -1.25.5B; I _{DC} <1.75mKA		GND-RST-V _{CC}
	MAX6347UR38	MAX	mrc	V _{TR} -3.8B; V _{DR} -1.25.5B; I _{DC} <1.75MKA	SOT23,SOD23	
	MAX6347UR39	MAX				GND-RST-V _{CC}
	MAX6347UR40	MAX	mrc	V _{IR} =3.9B; V _{DD} =1.25.5B; I _{DC} <1.75mKA		
	MAX6347UR41	MAX	mrc	V _{TR} =4.0B; V _{DD} =1.25.5B; I _{CC} <1.75mxA	S0T23,S0D23	
	Antick California (Antick)		mrc	V _{TR} =4.1B; V _{DD} =1.25.5B; I _{CC} <1.75mKA	S0T23,S0D23	
	MAX6347UR42	MAX	mrc	V _{TR} =4.2B; V _{DD} =1.25.5 B; I _{CC} <1.75 m/A	SOT23,SOD23	
A CONTRACTOR	MAX6347UR43	MAX	mrc	V _{IR} =4.3B; V _{DD} =1.25.5B; I _{CC} <1.75mkA	SOT23,SOD23	
	MAX6347UR44	MAX	mrc	V _{IR} =4.38B; V ₀₀ =1.25.5B; I ₀₀ <1.75 mkA	S0T23,S0D23	
	MAX6347UR45	MAX	mrc	V _{TR} =4.5B; V _{DD} =1.25.5B; I _{CC} <1.75mkA	S0T23,S0D23	
	MAX6347UR46	MAX	mrc	V _{TB} =4.6B; V _{DD} =1.25.5B; I _{CC} <1.75mkA		GND-RST-V _{CC}
	MAX6348UR33	MAX	mrc	V _{TR} =3.3B; V _{DD} =1.25.5B; I _{CC} <1.75mkA		GND · RST · V _{CC}
	MAX6348UR34	MAX	mrc	V _{TR} =3.4B; V _{DD} =1.25.5B; I _{CC} <1.75MKA		GND · RST · V _{CC}
FZBZ	MAX6348UR35	MAX	mrc	V _{TR} =3.5B; V _{DD} =1.25.5B; I _{CD} <1.75mkA	S0T23,S0D23	GND · RST · V _{CC}

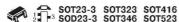
Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
FZCA	MAX6348UR36	MAX	mrc	V _{TR} =3.6B; V _{DD} =1.25.5B; I _{DD} <1.75 mKA	SOT23,SOD23	GND · RST · V _{CC}
FZCB	MAX6348UR37	MAX	mrc	V _{TB} =3.7B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA		GND · RST · V _{CC}
FZCC	MAX6348UR38	MAX	mrc	V _{TB} =3.8B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA		GND · RST · V _{CC}
	MAX6348UR39	MAX	mrc	V _{TR} =3.9B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA		GND · RST · V _{CC}
	MAX6348UR40	MAX	mrc	V _{TR} =4.0B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA		GND · RST · V _{CC}
-	MAX6348UR41	MAX	mrc	V _{TB} =4.1B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA		GND · RST · V _{CC}
FZCG	MAX6348UR42	MAX	mrc	V _{TR} =4.2B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA		GND · RST · Voc
	MAX6348UR43	MAX	mrc	V _{TR} =4.3B; V _{DD} =1.25.5B; I _{DG} <1.75 мкA		GND · RST · V _{CC}
	MAX6348UR44	MAX	mrc	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA		GND · RST · V _{CC}
	MAX6348UR45	MAX	mrc	V _{TR} =4.5B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA		GND · RST · V _{CC}
	MAX6348UR46	MAX	mrc	V _{TB} =4.6B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA		GND · RST · Voc
	MAX6332UR16D3	-	mrc	V _{TR} =1.6B; V _{DD} =1.25.5B; I _{CC} <7 мкA		GND · RST · V _{CC}
	MAX6332UR18D3		mrc	V _{TR} =1.8B; V _{DD} =1.25.5B; I _{DC} <7 mrA		GND · RST · V _{CC}
	MAX6332UR22D3		mrc	V _{TR} -2.2B; V _{DD} -1.25.5B; I _{DG} < 7 мкA		GND · RST · V _{CC}
	MAX6333UR16D3		mrc	V _{TR} =1.6B; V _{DD} =1.25.5B; I _{DD} <7 мкA		GND ·RST · V _{CC}
	MAX6333UR18D3	_	mrc	V _{TR} =1.8B; V _{DD} =1.25.5B; I _{CC} <7 мкA		GND · RST · V _{CC}
	MAX6333UR20D3		mrc	V _{TR} =2.0B; V _{DD} =1.25.5B; I _{DD} <7 mKA		GND ·RST · V _{CC}
-	MAX6333UR22D3		mrc	V _{TR} =2.2B; V _{DD} =1.25.5B; I _{CC} <7 MKA		GND ·RST · V _{CC}
	MAX6333UR23D3	1000	mrc	V _{TR} =2.3B; V _{DD} =1.25.5B; I _{CC} <7 мкA		GND ·RST · V _{CC}
	MAX6334UR16D3		mrc	V _{TR} =1.6B; V _{DD} =1.25.5B; I _{DC} <7 m/sA		GND · RST · V _{CC}
	MAX6334UR18D3		mrc	V _{TR} =1.8B; V _{DD} =1.25.5B; I _{DC} <7 m/sA		GND ·RST · V _{CC}
	MAX6334UR22D3	_	mrc	V _{TR} =2.2B; V _{OD} =1.25.5B; I _{OC} <7 MKA		GND · RST · V _{CC}
	MAX6001EUR	MAX	vref	V _{IN} =2.512.6B; I _{DUT} =±400 мкА; V _{DUT} =1.250B	SOT23,SOD23	
	MAZ6001UR	MAX	vref	V _{0.07} =1.250B	SOT23,SOD23	
-	MAX6002EUR	MAX	vref	V _{IN} =V _{DUT} +0.212.6B; I _{DUT} =±400 mKA; V _{DUT} =2.500B	SOT23,SOD23	
	MAZ6002UR	MAX	vref	V _{INIT} =2.500B	SOT23,SOD23	
	MAX6004EUR	MAX	vref	V _{IN} =V _{DUT} +0.212.6B; I _{DUT} =±400 мкА; V _{DUT} =4.096B	SOT23,SOD23	
	MAZ6004UR	MAX	vref	V _{CMT} =4.096B	SOT23,SOD23	
	MAX6005EUR	MAX	vref	V _{IN} =V _{DLT} +0.212.6B; I _{DLT} =±400 mKA; V _{DLT} =5.000B	SOT23,SOD23	
	MAZ6005UR	MAX	vref	V _{CUT} =5.000B	SOT23,SOD23	
-	MAX6012BEUR	MAX	vref		SOT23,SOD23	
0.000	MAX6025BEUR	MAX	vref	V_{IN} =2.512.6B; TC_{VDUT} <30 ppm/°C; V_{OUT} =1.247 B V_{IN} = V_{DUT} +0.212.6B; TC_{VDUT} <30 ppm/°C; V_{CUT} =2.500 B	SOT23,SOD23	
	MAX6041BEUR	MAX	vrei		SOT23,SOD23	
		MAX	-	V _{IN} =V _{DUT} +0.212.6B; TC _{VDUT} <30 ppm/*C; V _{DUT} =4.096B		
	MAX6045BEUR	MAX	vref	V _{IN} =V _{DUT} +0.212.6B; TC _{VDUT} <30 ppm/*C; V _{DUT} =4.500 B	SOT23,SOD23	
	MAX6050BEUR	_	vref	V _{IN} =V _{DUT} +0.212.6B; TC _{VDUT} <30.ppm/*C; V _{DUT} =5.000B	SOT23,SOD23	
	MAX6021BEUR	MAX	vref	V _{IN} =2.512.6B; TC _{VOUT} <30 ppm/°C; V _{OUT} =2.048B	SOT23,SOD23	
	MAX6003EUR		vref	V _{IN} =V _{DUT} +0.212.6B; I _{DUT} =±400 мкA; V _{DUT} =3.000B	SOT23,SOD23	
	MAZ6003UR	MAX	vref	V _{CUT} =3.000 B	SOT23,SOD23	2
-		MAX	mrc	V _{TR} =2.0B; V _{DD} =1.25.5B; I _{DC} <7 mrA		GND ·RST · V _{CC}
-	MAX6332UR23D3		mrc	V _{TR} =2.3B; V _{DD} =1.25.5B; I _{DC} <7 m/A		GND ·RST ·V _{CC}
	MAX6334UR20D3	_	mrc	V _{TR} =2.0B; V _{DD} =1.25.5B; I _{CC} <7 m/A	_	GND ·RST · V _{CC}
	MAX6334UR23D3		mrc	V _{TR} =2.3B; V _{DD} =1.25.5B; I _{CC} <7 mrA		GND · RST · V _{CC}
	MAX6806UR46	MAX	νd	V _{TR} =4.6B;V _{DD} =1.25.5B; I _{CC} <80 MKA		RST GND V _{CC}
	MAX6806UR26	MAX	Aq	V _{TR} =2.6B; V _{DD} =1.25.5B; I _{CC} <80 MKA		RST•GND•V _{GC}
	MAX6806UR23	MAX	vd	V _{TR} =2.3B; V _{DD} =1.25.5B; I _{CC} <80 mKA		RST GND V _{CC}
	MAX6807UR46	MAX	vd	V _{тп} =4.6B; V _{DD} =1.25.5B; I _{DC} <80 мкА		RST • GND • V _{CC}
2 0	MAX6807UR26	MAX	vd	V _{TR} =2.6B; V _{DD} =1.25.5B; I _{DC} <80 mKA		RST+GND+V _{GC}
_	MAX6808UR46	MAX	νd	V _{TR} =4.6B; V _{DD} =1.25.5B; I _{CC} <80 m/cA		RST · GND · V _{GC}
	MAX6808UR26	MAX	vd	V _{TR} =2.6B; V _{DD} =1.25.5B; I _{CC} <80 мкA		RST-GND-V _{CC}
	MAX6030AEUR	MAX	vref	V _{IN} =V _{OUT} +0.212.6B; TC _{VOUT} <20 ppm/"C; V _{OUT} =3.000B	SOT23,SOD23	
100.000	MAX6030BEUR	MAX	vref	V _{IN} =V _{OUT} + 0.212.6B; TC _{VOUT} < 30 ppm/"C; V _{OUT} =3.000B	SOT23,SOD23	
FZDY	MAX6334UR17D3	MAX	mrc	V _{TR} =1.7B; V _{DD} =1.25.5B; I _{CC} <7 мкA	SOT23,SOD23	GND · RST · V _{CC}





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
ZEA	MAX6333UR25D3	MAX	mrc	V _{TB} =2.5B; V _{DD} =1.25.5B; I _{CC} < 7 mKA	SOT23,SOD23	GND · RST · V _{CC}
ZEB	LM4041AIM3-1.2	MAX	vref	V _{OUT} =1.225 B; ACC=0.1 %	SOT23,SOD23	
	LM4041BIM3-1.2		vref	V ₀₁₀ =1.225 B; ACC=0.2 %	SOT23,SOD23	
	LM4041CIM3-1.2	_	vref	V _{OUT} =1.225 B; ACC=0.5 %	SOT23.SOD23	
ZEE	LM4041DIM3-1.2	MAX	vref	V _{DIT} =1.225 B; ACC=1.0 %	SOT23,SOD23	+•n.c.
ZEF	LM4040AIM3-2.1	MAX	vref	V _{OUT} =2.048 B; ACC=0.1%	SOT23,SOD23	+ •n.c.
ZEG	LM4040BIM3-2.1	MAX	vref	V ₀₁₇₇ =2.048 B; ACC=0.2%	SOT23,SOD23	+ •n.c.
ZEH	LM4040CIM3-2.1	MAX	vref	V _{DIT} =2.048 B; ACC=0.5%	SOT23,SOD23	+n.c.
ZEI	LM4040DIM3-2.1	MAX	vref	V _{DITT} =2.048 B; ACC=1.0%	SOT23,SOD23	+n.c.
ZEJ	LM4040AIM3-2.5	MAX	vref	V _{OUT} =2.500 B; ACC=0.1%	SOT23.SOD23	
ZEK		MAX	vref	V _{OUT} = 2.500 B; ACC=0.2%	SOT23,SOD23	
ZEL	LM4040CIM3-2.5	MAX	vref	V _{OUT} =2.500 B; ACC=0.5%	SOT23.SOD23	
		MAX	vref	V _{OUT} =2.500 B; ACC=1.0%	SOT23,SOD23	1200000
ZEN	LM4040AIM3-3.0	MAX	vref	V _{OIT} =3.000 B; ACC=0.1%	SOT23,SOD23	11 22/10030
		MAX	vref	V _{DIT} =3.000 B; ACC=0.2%	SOT23,SOD23	-
ZEP	LM4040CIM3-3.0	MAX	vref	V _{DIT} =3.000 B; ACC=0.5%	SOT23,SOD23	
_		MAX	vref	Voirt=3.000 B: ACC=1.0%	SOT23,SOD23	
	LM4040AIM3-4.1	MAX	vref	V _{OUT} =4.096 B; ACC=0.1%	SOT23.SOD23	
	LM4040BIM3-4.1	MAX	vref	V _{OIT} =4.096 B; ACC=0.2%	SOT23,SOD23	0.0000
ZET	LM4040CIM3-4.1	MAX	vref	V _{OUT} =4.096 B; ACC=0.5%	SOT23,SOD23	100000
	LM4040DIM3-4.1	MAX	vref	V _{OUT} =4.096 B; ACC=1.0%	SOT23,SOD23	10000
ZEV	LM4040AIM3-5.0	MAX	vref	V _{OIIT} =5.000 B; ACC=0.1%	SOT23,SOD23	
	LM4040BIM3-5.0	MAX	vref	V _{0.07} -5.000 B; ACC=0.2%	SOT23,SOD23	
ZEX	LM4040CIM3-5.0	MAX	vref	V _{OLIT} =5.000 B; ACC=0.5%	SOT23,50D23	
ZEY	LM4040CIM3-5.0	MAX	vref	V _{OIIT} =5.000 B; ACC=1.0%	SOT23,SOD23	
	MAZ803LUR	MAX	mrc	V _{TR} =5.0B	SOT23,SOD23	
	MAZ803MUR	MAX	2000		SOT23,SOD23	
_	MAZ803TUR		mrc	V _{IR} *5.0B		
		MAX	mrc	V _{IR} :3.3B	SOT23,SOD23	
	MAZ803SUR	MAX	mrc	V _{IR} :3.3B	SOT23,SOD23	
-	MAZ803RUR	MAX	mrc	V _{TR} :3.0B	SOT23,SOD23	
	MAX6808UR32	MAX	vd .	V _{TR} =3.2B; V _{DD} =1.25.5 B; I _{CC} <80 мкА	SOT23,SOD23	- 01
	MAX6066AEUR	MAX	vref	V _{IN} =V _{DUT} +0.212.6B; TC _{VOUT} <20 ppm/°C; V _{DUT} =2.500B	SOT23,SOD23	
	MAX6066BEUR	MAX	vref	V _{IN} =V _{CUT} +0.212.6B; ΤС _{VOUT} <30 ppm/°C; V _{OUT} =2.500B	SOT23,SOD23	
	MAX6061AEUR	MAX	vref	V _{IN} =2.512.6B; TC _{VOUT} < 20 ppm/°C; V _{DUT} =1.248B	SOT23,SOD23	
	MAX6061BEUR	MAX	vref	V _{IN} =2.512.6B; TC _{VOUT} <30 ppm/°C; V _{DUT} =1.248B	SOT23,SOD23	
	MAX6067AEUR	MAX	vref	V _{IN} =V _{CUT} + 0.212.6B; TC _{VOUT} < 20 ppm/°C; V _{DUT} =4.500B	SOT23,SOD23	
	MAX6067BEUR	MAX	vref	V _{IN} =V _{CUT} + 0.212.6B; TC _{VOUT} < 30 ppm/°C; V _{DUT} =4.500B	SOT23,SOD23	
	MAX6063AEUR	MAX	vref	V _{IN} =V _{DUT} + 0.2 12.6 B; TC _{VOUT} < 20 ppm/°C; V _{DUT} =3.000 B	SOT23,SOD23	
	MAX6063BEUR	MAX	vref	V _{IN} =V _{CUT} + 0.212.6B; TC _{VOUT} < 30 ppm/°C; V _{DUT} =3.000B	SOT23,SOD23	
ZFY	MAX6062AEUR	MAX	vref	V _{IN} =2.512.6B;R[-33]CTC _{VOUT} <20 ppm/°C; V _{OUT} =2.048B	SOT23,SOD23	
	MAX6062BEUR	MAX	vref	V _{IN} =2.512.6B; TC _{VOUT} <30 ppm/°C; V _{DUT} =2.048B	SOT23,SOD23	
	MAX6064AEUR	MAX	vref	V _{IN} =V _{CUT} + 0.2 12.6 B; TC _{VOUT} < 20 ppm/°C; V _{DUT} =4.096 B	SOT23,SOD23	
	MAX6064BEUR	MAX	vref	V _{IN} =V _{OUT} + 0.212.6B; TC _{VOUT} < 30 ppm/°C; V _{OUT} = 4.096B	SOT23,SOD23	100000000000000000000000000000000000000
	MAX6065AEUR	MAX	vref	V _{IN} =V _{OUT} + 0.212.6B; TC _{VOUT} < 20 ppm/°C; V _{OUT} =5.000B	SOT23,SOD23	
	MAX6065BEUR	MAX	vref	V _{IN} =V _{OUT} + 0.2 12.6 B; ΤС _{VOUT} < 30 ppm/°C; V _{OUT} = 5.000 B	SOT23,SOD23	
	MAX6006AEUR	MAX	vref	ACC=0.2%; I _{OUT} =±400 mkA; V _{OUT} =1.25B	SOT23,SOD23	
	MAZ6006AUR	MAX	vref	V _{OUT} =1.250 B; ACC=0.2%	SOT23,SOD23	
ZGI	MAX6006BEUR	MAX	vref	ACC=0.5%; I _{DUT} =±400 mkA; V _{DUT} =1.25B	SOT23,SOD23	OUT GND i.c.
	MAZ6006BUR	MAX	vref	V _{OUT} -1.250 B; ACC=0.5%	SOT23,SOD23	+ ·n.c.
ZGJ	MAZ6006CUR	MAX	vref	V _{OUT} =1.250 B; ACC=1.0%	SOT23,SOD23	+ •n.c.
ZGK	MAX6007AEUR	MAX	vref	ACC=0.2%; I _{OUT} =±400 mKA; V _{OUT} =2.048 B	SOT23,SOD23	OUT · GND · i.c.
704	MAZ6007AUR	MAX	vref	V _{OUT} =2.480 B; ACC=0.2%	SOT23,SOD23	+n.c

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
FZGL	MAX6007BEUR	MAX	vref	ACC=0.5%; I _{DIT} =±400 MKA; V _{DIT} =2.048 B	SOT23,SOD23	OUT · GND · i.c.
FZGL	MAZ6007BUR	MAX	vref	V _{rvn} =2.480 B; ACC=0.5%	SOT23,SOD23	+n.c.
FZGM	MAZ6007CUR	MAX	vref	V _{0XII} =2.480 B; ACC=1.0%	SOT23,SOD23	+n.c.
	MAX6008AEUR	MAX	vref	ACC=0.2%; I _{DUT} =±400 mKA; V _{DUT} =2.5 B	SOT23,SOD23	
	MAZ6008AUR	MAX	vref	V _{OUT} =2.500 B; ACC=0.2%	SOT23,SOD23	
	MAX6008BEUR	MAX	vref	ACC=0.5%; I _{DITI} =±400 мкА; V _{DITI} =2.5 B	SOT23,SOD23	
	MAZ6008BUR	MAX	vref	V _{OLIT} =2.500 B; ACC=0.5%	SOT23,SOD23	1000 CO-000 CO
	MAZ6008CUR	MAX	vref	V _{O.II} =2.500 B; ACC=1.0%	SOT23,SOD23	
	MAX6009AEUR	MAX	vref	ACC=0.2%; I _{DUT} =±400 mKA; V _{DUT} =3.0 B	SOT23,SOD23	
	MAZ6009AUR	MAX	vref	V _{CMT} =3.000 B; ACC=0.2%	SOT23,SOD23	
	MAX6009BEUR	MAX	vref	ACC=0.5%; I _{DUT} =±400 мкА; V _{DUT} =3.0 B	SOT23,SOD23	
	MAZ6009BUR	MAX	vref	V _{олт} =3.000 В; ACC=0.5%	SOT23,SOD23	
	MAZ6009CUR	MAX	vref	V _{CUT} =3.000 B; ACC=1.0%	SOT23,SOD23	
FZGT	MAX6101EUR	MAX	vref	V _{IN} =2.512.6B; I _{GG} <125 _{MK} A; V _{OUT} =1.250B	SOT23,SOD23	
-	MAX6102EUR	MAX	vref	V _{IN} =V _{DUT} +0.212.6B; I _{CC} < 125 mkA; V _{OUT} =2.500B	SOT23,SOD23	
FZGV		MAX	vref		SOT23,SOD23	
	MAX6103EUR MAX6104EUR	MAX	vref	$V_{IN}^{2}V_{OUT}^{2} + 0.212.6B; I_{CC}^{2} + 125 mKA; V_{OUT}^{2} + 3.000B$ $V_{IN}^{2}V_{OUT}^{2} + 0.212.6B; I_{CC}^{2} + 125 mKA; V_{OUT}^{2} + 4.096B$	SOT23,SOD23	
FZGX		MAX	vref		SOT23,SOD23	
	MAX6105EUR	10000	2000	V _{IN} =V _{DUT} +0.212.6B; I _{CC} <125mkA; V _{DUT} =5.000B		
FZGY FZHA		MAX	mrc	V _{TR} =1.6B; V _{DD} =1.25.5B; I _{CC} <7 мкА	SOT23,SOD23	
			mrc	V _{TR} =2.4B; V _{DD} =1.25.5B; I _{CC} <7 m/A	SOT23,SOD23	
	MAX6375UR26	MAX	vd	V _{TR} =2.63B; V _{DD} =1.25.5B; I _{CC} <1.75 mKA	SOT23,SOD23	
FZHD	MAX6375UR22	MAX	Aq	V _{TR} =2.20B; V _{DD} =1.25.5B; I _{CC} <1.75 MKA	SOT23,SOD23	
	MAX6375UR23	MAX	vd	V _{TR} =2.32B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	
FZHF	MAX6375UR29	MAX	vd	V _{TR} =2.93B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA	SOT23,SOD23	- 00
	MAX6375UR31	MAX	₩d	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	
	MAX6376UR22	MAX	Aq	V _{TR} =2.20B; V _{DD} =1.25.5B; I _{CC} <1.75 mKA	SOT23,SOD23	
FZHI	MAX6376UR23	MAX	vd	V _{TR} =2.32B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	
	MAX6376UR26	MAX	vd	V _{TR} =2.63B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA	SOT23,SOD23	
	MAX6376UR29	MAX	٧d	V _{TR} =2.93B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA	SOT23,SOD23	
FZHL	MAX6376UR31	MAX	νd	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA	SOT23,SOD23	
	MAX6377UR22	MAX	vd	V _{TR} =2.20B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	
	MAX6377UR23	MAX	vd	V _{TR} =2.32B; V _{DD} =1.25.5B; I _{CC} <1.75 mkA	SOT23,SOD23	
	MAX6377UR26	MAX	Aq	V _{TR} =2.63B; V _{DD} =1.25.5B; I _{CC} <1.75 mKA	SOT23,SOD23	
FZHP	MAX6377UR29	MAX	vd	V _{TR} =2.93B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	
	MAX6377UR31	MAX	vd	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{CC} <1.75 mKA	SOT23,SOD23	
	MAX6377UR27	MAX	Aq	V _{TR} =2.70B; V _{DD} =1.25.5B; I _{CC} <1.75 мкA	SOT23,SOD23	
	MAX6377UR24	MAX	νd	V _{TR} =2.40B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	
FZHT	MAX6377UR28	MAX	vd	V _{TR} =2.80B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	
FZHU	MAX6378UR44	MAX	vd	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	OUT · GND · V _{CI}
FZHV	MAX6378UR46	MAX	vd	V _{TR} =4.63B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	
FZHW	MAX6379UR44	MAX	٧d	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	
FZHX	MAX6379UR46	MAX	vd	V _{TR} =4.63B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	
FZHY	MAX6380UR44	MAX	νd	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	OUT · GND · V _C
FZHZ	MAX6380UR46	MAX	νd	V _{TR} = 4.63 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 мкA	SOT23,SOD23	
FZIA	MAX6380UR42	MAX	vd	V _{TR} =4.20B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	SOT23,SOD23	OUT · GND · V _C
FZIB	MAX6068AEUR	MAX	vref	V _{IN} =V _{DUT} +0.212.6B; TC _{VDUT} <20 ppm/*C; V _{DUT} =1.800 B	SOT23,SOD23	IN+OUT+GND
FZIC	MAX6068BEUR	MAX	vref	V _{IN} =V _{DUT} +0.212.6B; TC _{VDUT} <30 ppm/*C; V _{DUT} =1.800 B	SOT23,SOD23	IN-OUT-GND
FZID	MAX6100EUR	MAX	vref	V _{IN} =2.512.6B; I _{CC} <125 _{MK} A; V _{OUT} =1.800B	SOT23,SOD23	IN-OUT-GND
FZIE	MAX6800UR26D3	MAX	mrc	V _{тн} =2.63B; V _{DD} =1.25.5B; I _{CC} <12мкА	SOT23,SOD23	GND · RST · V _c
FZIF	MAX6800UR29D3	MAX	mrc	V _{TR} =2.93B; V _{DD} =1.25.5B; I _{CC} <12mkA	SOT23,SOD23	
FZIG	MAX6800UR31D3		mrc	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{CC} <12мкА	SOT23,SOD23	
FZIH	MAX6800UR44D3		mrc	V _{тв} =4.38B; V _{пп} =1.25.5B; I _{пп} <12мкА	SOT23,SOD23	





Код	Типономинал	Б	ф	Особенности	Корпус	Ц: 1•2•3
FZII	MAX6800UR46D3	MAX	mrc	V _{TR} =4.63B; V _{DD} =1.25.5B; I _{CC} <12 мкА	SOT23,SOD23	GND · RST · V _{CC}
FZIK	MAX6801UR26D3	MAX	mrc	V _{TB} =2.63B; V _{DD} =1.25.5B; I _{DC} <12 мкА	SOT23,SOD23	GND+RST+V _{CC}
FZIL	MAX6801UR29D2	MAX	mrc	V _{TB} =2.93B; V _{DD} =1.25.5B; I _{DC} <12 mKA		GND · RST · V _{CC}
FZIM	MAX6801UR29D3	_	mrc	V _{TB} =2.93B; V _{DD} =1.25.5B; I _{DC} <12 мкА		GND-RST-V _{CC}
FZIN	MAX6801UR31D3	MAX	mrc	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{DC} <12 mKA		GND-RST-V _{CC}
FZIO	MAX6801UR44D3	MAX	mrc	V _{TB} =4.38B; V _{DD} =1.25.5B; I _{DC} < 12 мкА		GND · RST · V _{CC}
FZIP	MAX6801UR46D3	MAX	mrc	V _{TR} =4.63B; V _{DD} =1.25.5B; I _{DC} <12 mKA		GND · RST · V _{CC}
FZIQ	MAX6802UR26D3	MAX	mrc	V _{TR} =2.63B; V _{DD} =1.25.5B; I _{DC} <12 mkA		GND-RST-V _{CC}
FZIS	MAX6802UR31D3	MAX	mrc	V _{TB} =3.08B; V _{DD} =1.25.5B; I _{DC} <12 мкА		GND+RST+V _{CC}
FZIT	MAX6802UR44D3	MAX	mrc	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <12 mKA		GND · RST · V _{CC}
FZIU		MAX	mrc	V _{TB} =4.63B; V _{DD} =1.25.5B; I _{DC} <12 mKA		GND-RST-V _{CC}
FZJR	MAX6106EUR	MAX	vref	V _{IN} =2.512.6B; I _{CC} <125mrA; V _{OUT} =2.048B	SOT23.SOD23	- 00
FZMV	MAX6107EUR	MAX	vref	V _{IN} =V _{CLIT} +0.212.6B; I _{CC} <125 mrA; V _{CLIT} =4.500 B	SOT23,SOD23	IN-OUT-GND
G	IRLML2502	IR	nMOS	HEXFET; V _{DS} =30 B; I _D =3.4A; P _D =1.25 BT; R _{DS(on)} < 0.08 OM	SOT23.SOD23	
G	MRF947AT1	мот	non	V _{CR0} =20B; I _C =50 MA; P _D =188 MBT; h ₂₁ =75150; f _T =8 ГГц	SOT323.SC70	B·E·C
GO	HSMP3890	HP	pin	I _E <1A; P _D <250 мВт; V _{BB} >100 В; R _S <2.5 Ом; C _D <0.30 пФ	SOT23 SOD23	
GO	HSMP389B	HP	oin	I _E <1A; V _{PR} >100B; R _S <2.50m; CT<0.30 nΦ	SOT323,SC70	A·n.c.·K
G08	DTD133HK	ROHM	Dnon	V _{CB0} =50B; I _C =500 MA; P _D =200 MBT; I _{D1} >56; f _T >200 MFц;	SOT346,SC59	100000000000000000000000000000000000000
230000				R ₁ /R ₂ =3.3/10 кОм		
G1	BFS20	ZETEX	npn	$V_{CB0}=30B$; $I_C=25$ MA; $P_D=330$ MBT; $h_{21}=4085$; $f_T>450$ MF I_L	SOT23,SOD23	1000
G1	MMBT5551	MOT	npn	V _{CB0} =160 B; I _C =600 mA; P _D =300 mBt; h ₂₁ =80250	SOT23,SOD23	B·E·C
G1	MMBZ5226BT	DIODS	dz	V _Z (I _{ZT} =20 mA)=3.143.47 B; I _R <25 mrA	SOT523	A•n.c.•K
G10	NDS0610	NS	pMOS	V _{DS} =60 B; I _D =120 мА; Р _D =360 мВт; R _{DS(on)} <300 м	SOT23,SOD23	G·S·D
G11	DTB113ZK	ROHM	Dpnp	V_{CB0} =50B; I_C =500 MA; P_D =200 MBT; h_{21} >56; f_T >200 MFu; R_1/R_2 =1/10 kOM	SOT346,SC59	B·E·C
G17	MMBZ4617	VISH	dz	$V_Z(I_{ZT}=250 \text{ m/sA})=2.4 \text{ B}; Z_{ZT}(I_{ZT}=250 \text{ m/sA}) \le 1400 \text{ Om}$	SOT23,SOD23	A•n.c.•K
G18	MMBZ4618	VISH	dz	$V_Z(I_{ZT}=250 \text{ m/sA})=2.7 \text{ B}; Z_{ZT}(I_{ZT}=250 \text{ m/sA}) \le 1500 \text{ Om}$	SOT23,SOD23	Arn.c.rK
G19	MMBZ4619	VISH	dz	$V_Z(I_{ZT}=250 \text{ m/sA})=3.0 \text{ B}; Z_{ZT}(I_{ZT}=250 \text{ m/sA}) \le 1600 \text{ Dm}$	SOT23,SOD23	A+n.c.+K
G1E	BC847A	ROHM	non	V _{CB0} =50B; I _C =100мA; P _D =200мBт; h ₂₁ =110220; f _T =200МГц	SOT23,SOD23	B·E·C
G1F	BC847B	ROHM	npn	V _{CB0} =50B; I _C =100мA; P _D =200мBт; h ₂₁ =200450; f _T =200МГц	SOT23,SOD23	B·E·C
G1G	BC847C	ROHM	npn	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBr; h ₂₁ =420800; f _T =200 MFu,	SOT23,SOD23	B·E·C
G1J	BC848A	ROHM	npn	V _{CB0} =30 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =110220; f _T =200 МГц	SOT23,SOD23	B-E-C
G1K	BC848B	ROHM	npn	V _{CB0} =30B; I _C =100мA; P ₀ =250мBт; h ₂₁ =200450; f _T =200МГц	SOT23,SOD23	B·E·C
G1K	BC848BW	ROHM	npn	V _{CB0} =30B; I _C =100 мA; P _D =250 мВт; h ₂₁ =200450; f _T =200 МГц	SOT323,SC70	B·E·C
G1L	BC848C	ROHM	npn	V_{CB0} =30B; I_C =100 mA; P_D =250 mBT; h_{21} =420800; f_T =200 MFu	SOT23,SOD23	B·E·C
G1p	BFS20	PHIL	npn	V_{CB0} =30B; I_C =25 mA; P_D =250 mBT; h_{21} >40; f_T =450 MFu	SOT23,SOD23	B·E·C
G1t	HSMP3891	HP	pin	$I_F \le 1 \text{A}, P_D \le 250 \text{ MBT}, V_{BR} \ge 100 \text{ B}, R_S \le 2.5 \text{ OM}, C_D \le 0.30 \text{ n} \Phi$	SOT23,SOD23	n.c. • A • K
G2	HSMP3892	HP	pin×2	I_F < 1 A; P_D < 250 мВт; V_{BR} > 100 B; P_S < 2.5 Ом; C_D < 0.30 пФ	SOT23,SOD23	A1 • K2 • K1,A2
G2	HSMP389C	HP	pin×2	I _F <1A; V _{BR} >100B; R _S <2.50м; СТ<0.30пФ	SOT323,SC70	
G2	MMBZ5227BT	DIODS	dz	V _Z (I _{ZT} =20 mA)=3.423.78 B; I _B <15 mrA	SOT523	A+n.c.+K
G20	MMBZ4620	VISH	dz	V _Z (I _{ZT} =250 m;A)=3.3 B; Z _{ZT} (I _{ZT} =250 m;A) < 1650 Om	SOT23,SOD23	A+n.c.+K
G21	DTD113ZK	ROHM	Dnpn	V_{CB0} =50 B; I_C =500 mA; P_D =200 mBt; h_{21} >56; f_T >200 MFu; R_1/R_2 =1/10 kOm	SOT346,SC59	B·E·C
G21	DTD113ZU	ROHM	Dnpn	V_{CB0} =50 B; I_C =500 MA; P_D =200 MBT; h_{21} >56; f_T >200 MFц; R_1/R_2 =1/10 кОм	S0T323,SC70	
G21	MMBZ4621	VISH	dz	V _Z (I _{ZT} =250 mkA}=3.6 B; Z _{ZT} (I _{ZT} =250 mkA} < 1700 Om	SOT23,SOD23	A•n.c.•K
G22	MMBZ4622	VISH	dz	V _Z (I _{ZT} =250 мкA)=3.9 B; Z _{ZT} (I _{ZT} =250 мкA) < 1650 Ом	SOT23,SOD23	170100000000000000000000000000000000000
G23	MMBZ4623	VISH	dz	V _Z (I _{ZT} =250 mkA)=4.3 B; Z _{ZT} (I _{ZT} =250 mkA) < 1600 Om	SOT23,SOD23	A•n.c.•K
G24	MMBZ4624	VISH	dz	$V_Z(I_{ZT}=250 \text{ m/sA})=4.7 \text{ B}; Z_{ZT}(I_{ZT}=250 \text{ m/sA}) \le 1550 \text{ Om}$	SOT23,SOD23	A•n.c.•K
G25	MMBZ4625	VISH	dz	$V_Z(I_{ZT}=250 \text{ m/sA})=5.1 \text{ B}; Z_{ZT}(I_{ZT}=250 \text{ m/sA}) \le 1500 \text{ Om}$	SOT23,SOD23	A•n.c.•K
G26	MMBZ4626	VISH	dz	V _Z (I _{ZT} =250 m;A}=5.6 B; Z _{ZT} (I _{ZT} =250 m;A} < 1400 Om	SOT23,SOD23	A+n.c.+K
G27	MMBZ4627	VISH	dz	V _Z (I _{ZT} =250 mxA)=6.2 B; Z _{ZT} (I _{ZT} =250 mxA) < 1200 Om	SOT23,SOD23	A+n.c.+K
G3	1SS196	TOSH	di	$V_R \le 80 B$; $I_F \le 100 \text{ mA}$; $V_F (I_{F^2} = 100 \text{ mA}) \le 1.2 B$; $I_R \le 0.5 \text{ mKA}$; $t_{FR} \le 4 \text{ HC}$	SOT346,SC59	n.c.+A+K
G3	BAR63	SIEM	pin	$V_R \le 50 B$; $I_F \le 100 \text{ mA}$; $V_F (I_F = 100 \text{ mA}) \le 1.2 B$; $I_R \le 0.05 \text{ m/A}$; $C_D \le 0.3 \text{ n}$	SOT23,SOD23	A+n.c.+K
G3	HSMP3893	HP	pin×2	I _F < 1 A; P _D < 250 мВт; V _{BR} > 100 B; R _S < 2.5 Ом; C _D < 0.30 пФ	SOT23,SOD23	K1-K2-A1,A2

Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3
G3	HSMP389E	HP	pin×2	I _E <1A; V _{BR} >100B; R _S <2.5 O _M ; CT<0.30 nΦ	SOT323,SC70	K1-K2-A1,A2
G3	MMBZ5228BT	DIODS	dz	V ₂ (I ₂₁ =20 mA)=3.714.10B; I _B <10 mxA	SOT523	A·n.c.·K
-G3	PMST5551	PHIL	npn	V _{CR0} =180 B; I _C =600 mA; P _D =200 mBr; h _{P1} =80250; f _T =100300 MFu	SOT323,SC70	B·E·C
G3C	DTB122JK	ROHM	Dpnp	V_{C80} =50 B; I_c =500 MA; P_0 =200 MBT; h_{21} >47; f_T >250 MFu; R_1/R_2 =0.22/4.7 KOM	SOT346,SC59	B-E-C
G3E	BC857A	ROHM	pnp	V _{CB0} =50 B; I _C =100 мА; P ₀ =330 мВт; h ₂₁ =125250; f _T >150 МГц	SOT23,SOD23	B·E·C
G3F	BC857B	ROHM	pnp	V _{CB0} =50 B; I _C =100 мA; P ₀ =330 мВт; h ₂₁ =220475; f _T >150 МГц	SOT23,SOD23	B·E·C
G3FQ	2SA1037AKQLT1	LRC	pnp	V _{CB0} =50 B; I _C =150 мA; P _D =200 мВт; h ₂₁ =120270; f _T >140 МГц	SOT23,SOD23	B-E-C
G3FR	2SA1037AKRLT1	LRC	pnp	V _{GB0} =50 B; I _G =150 мА; P _D =200 мВт; h ₂₁ =180390; f _T >140 МГц	SOT23,SOD23	B-E-C
G3FS	2SA1037AKSLT1	LRC	pnp	V _{сво} =50 B; I _C =150 мА; P _D =200 мВт; h ₂₁ =270560; f _T >140 МГц	SOT23,SOD23	B·E·C
G3J	BC858A	ROHM	pnp	V ₀₈₀ =30 B; I _C =100 мA; P _D =300 мВт; h ₂₁ =125250; f _T >100 МГц	SOT23,SOD23	B·E·C
G3K	BC858B	ROHM	ono	V _{сво} =30 B; I _с =100 мА; P _D =310 мВт; h ₂₁ =200450; f _T >150 МГц	SOT23,SOD23	B-E-C
G3K	BC858BW	ROHM	ono	V _{CB0} =30B; I _C =100 мA; P _D =250 мВт; h ₂₁ =220475; f _T =250 МГц	SOT323,SC70	B-E-C
G3L	BC858C	ROHM	pnp	V _{C80} =30B; I _C =100 мА; P _D =300 мВт; h ₂₁ =420800; f _T >100 МГц	SOT23.SOD23	B·E·C
G4	BAR6304	SIEM	pin×2	V _B <50 B; I _E <100 мA; V _E (I _E =100 мA)<1.2 B; I _B <0.05 мкA; C _D <0.3 пФ	SOT23,SOD23	A1-K2-K1.A2
G4	BFS20R	PHIL	non	V _{CR0} =30B; I _C =25 mA; P _D =250 mBT; h ₂₁ >40; f _T =450 MFu	SOT23,SOD23	
G4	HSMP3894	HP	pin×2	I _E <1A; Р _П <250 мВт; V _{BR} >100 В; R _S <2.5 Ом; С _П <0.30 пФ	SOT23,SOD23	
G4	HSMP389F	HP	oin×2	I _E <1A; V _{BB} >100B; R _S <2.5 O _M ; CT<0.30 nΦ		A1 · A2 · K1 . K2
G4	MMBZ5229BT	DIODS	dz	V ₂ (I ₂₇ =20 mA)=4.09452B; I ₆ <5 mKA	SOT523	A·n.c.·K
G4C	DTD122JK	ROHM	Dnpn	V_{C80} =50 B; I_C =500 mA; P_D =200 mBr; h_{21} >47; f_T >200 MFu; P_T/P_D =0.22/4.7 kOm	SOT23,SOD23	10000000000
G4C	DTD122JK	ROHM	Dnpn	V _{CB0} =50 B; I _C =500 MA; P _D =200 MBT; h ₂₁ >47; f _T >200 MFu; P _T :/P _D =0.22*4.7 KOM	SOT346,SC59	B-E-C
G4s	BAR63-04	INF	pin×2	Ve < 50 B; le < 100 mA; Ve(le=100 mA) < 1.2 B; le < 0.01 mkA	SOT23,SOD23	A1-K2-K1.A2
G4s	BAR63-04W	INF	pin×2	VB < 50 B; IE < 100 mA; VE(IE=100 mA) < 1.2 B; IB < 0.01 mKA		A1-K2-K1.A2
G5	BAR6305	SIEM	pin×2	V _R <50B; I _E <100mA; V _E (I _E =100 mA)<1.2B; I _B <0.05mkA; C _D <0.3πΦ	SOT23.SOD23	A1-A2-K1.A2
G5	MMBZ5230BT	DIODS	dz	V ₂ (I _{ZT} =20 mA)=4.474.94B; I _R <5 mkA	SOT523	A·n.c.·K
G5s	BAR63-05	INF	pin×2	Ve < 50 B: le < 100 mA: Ve(le=100 mA) < 1.2 B: le < 0.01 mkA	SOT23.SOD23	A1-A2-K1.K2
G5s	BAR63-05W	INF	pin×2	Ve < 50 B; le < 100 mA; Ve(le=100 mA) < 1.2 B; le < 0.01 mkA	SOT323.SC70	A1-A2-K1.K2
G6	BAR6306	SIEM	pin×2	V _B <50 B; I _E <100 mA; V _E (I _E =100 mA)<1.2 B; I _B <0.05 mkA; C _B <0.3 πΦ	SOT23,SOD23	K1-K2-A1.A2
G6A	BC817-16	TOSH	non	V _{сво} =50 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =100250; f _T =150 МГц	SOT23,SOD23	The second second
G6B	BC817-25	TOSH	ngn	V _{CBO} =50 B; I _C =800 мA; P _D =330 мВт; h ₂₁ =160400; f _T =150 МГц	SOT23,SOD23	
G6s	BAR63-06	INF	pin×2	V _R <50B; I _E <100 mA; V _E (I _E =100 mA)<1.2 B; I _R <0.01 mkA	SOT23,SOD23	1.3
G6s	BAR63-06W	INF	pin×2	V _B <50 B; I _E <100 mA; V _E (I _E =100 mA)<1.2 B; I _B <0.01 mKA	SOT323.SC70	
G7	BF579	VIS	ono	V _{CSB} =20B; I _C =25мA; P _D =200 мВт; h ₂₁ =2090; f _T =1750 МГц	SOT23,SOD23	
G98	DTB133HK	ROHM	Dpnp	V_{C80} =50B; I_C =500 mA; P_D =200 mBr; h_{21} >56; f_T >200 MF $_U$; P_{11} / P_{22} =3.3/10 kOm	SOT346,SC59	100 100 100
GA	HSMP4890	HP	pin	$I_F \le 1 A$; $P_D \le 250 \text{ mBT}$; $V_{BB} \ge 100 \text{ B}$; $R_S \le 2.50 \text{ m}$; $C_D \le 0.375 \text{ m}\Phi$; $L_{T} = 1.0 \text{ H}\Gamma$	SOT23,SOD23	A-A-K
GAB	BCW60B	ROHM	non	V _{CR0} =32 B; I _C =200 мA; P _D =330 мВт; h ₂₁ =180310; f _T >250 МГц	SOT23.SOD23	B-E-C
GAC	BCW60C	ROHM	non	V ₀₈₀ =32 B; I _C =200 мA; P _D =330 мВт; h ₂₁ =250460; f _T >250 МГц	SOT23,SOD23	B-E-C
GAD	BCW60D	ROHM	non	V _{CRO} =32 B; I _C =200 MA; P _D =330 MBT; h _{P1} =380630; f _T >250 MFu	SOT23,SOD23	_
GAH	BCX70H	ROHM	non	V _{CB0} =45B; I _C =200 MA; P ₀ =330 MBr; h ₂₁ =180310; f ₁ >250 MFu	SOT23,SOD23	
GAJ	BCX70J	ROHM	non	V _{CB0} =45B; I _C =200 MA; P _D =330 MBr; h ₂₁ =250460; f _T >250 MFu	SOT23,SOD23	
GAK	BCX70K	ROHM	nan	V _{CR0} =45 B; I _C =200 MA; P _D =330 MBT; h ₂₁ =380630; f _T >250 MFu	SOT23,SOD23	100000000000000000000000000000000000000
GBB	BCW61B	ROHM	ono	V _{CR0} =32 B; I _C =100 мA; P _D =330 мВт; h ₂₁ =180310; f _T =250 МГц	SOT23,SOD23	
GBC	BCW61C	ROHM	ono	V _{DB0} =32B; I _C =200 MA; P _D =330 MBT; h ₂₁ =250460; f _T >180 MFu	SOT23,SOD23	
GBG	BCX71G	ROHM	ono	V _{C80} =45B; I _C =100 MA; P _D =330 MBr; h ₂₁ =120220; f _T =250 MFu	SOT23,SOD23	
GBH	BCX71H	ROHM	ono	V _{D80} =45 B; I _C =200 MA; P _D =330 MBT; h ₂₁ =180310; f _T >180 MFu	SOT23,SOD23	
GBJ	BCX71J	ROHM	pnp	V _{CBB} =455, I _C =200 MA; P _B =330 MBT; h ₂₁ =250460; f _T >180 MFu	SOT23,SOD23	
GC	2SC2734	REN	ngn	V _{CR0} =20B; I _C =50 MA; P _D =150 MBT; I _{P2} =20200; I _T >140 MT;	SOT346.SC59	100000000000000000000000000000000000000
GC	2SC4264	REN	ngn	V _{CR0} =20B; I _C =50 MA; P _D =100 MB1; I _{D1} =20200; I _T >1.41 Tu	SOT323.SC70	-0.00
GC1	BCW29	ROHM	ono		SOT23.SOD23	TO 15
OK I	DUNES	HUMIN	hub	V_{C80} =30 B; I_C =100 MA; P_0 =350 MBr; h_{C1} =120260 V_{C80} =30 B; I_C =100 MA; P_0 =330 MBr; h_{C1} =215500; f_T >150 MFu	00120,00023	D.E.O





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
GD1	BCW31	ROHM	npn	V _{CB0} =32B; I _C =100 mA; P _D =330 mBT; h ₂₁ =110220; f _T >300 MFu,	SOT23,SOD23	B·E·C
GD2	BCW32	ROHM	npn	V _{CR0} =32 B; I _C = 100 мА; P _D =330 мВт; h ₂₁ =200450; f _T >300 МГц	SOT23,SOD23	B·E·C
GD3	BCW33	ROHM	non	V _{CR0} =32 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =420800; f _T >300 МГц	SOT23.SOD23	B·E·C
GE	2SA1455KE	ROHM	onp	V _{CR0} =120B; I _C =50mA; P _D =200mBT; h ₂₁ =390820; f _T >140 MFu	SOT346.SC59	B-E-C
GEC	BCW65C	ROHM	non	V _{CB0} =60 B; I _C =800 мА; P _D =330 мВт; h ₂₁ =250630; f _T >100 МГц	SOT23,SOD23	B·E·C
GEs	BFR35AP	SIEM	non	V _{CPO} =20B; I _C =30 MA; P _D =280 MBT; h ₂₁ =40200; f _T =5000 MFц	SOT23.SOD23	B·E·C
GFs	BFR92P	SIEM	non	V _{CR0} =20 B; I _C =30 мA; P _D =280 мВт; h ₂₁ =40200; f _T =5000 МГц	SOT23.SOD23	B·E·C
GG	BF579R	VIS	onp	V _{GR0} =20 B; I _G =25 mA; P _D =200 mBT; h ₂₁ =2090; f ₇ =1750 MFu	SOT23 SOD23	F·B·C
GG	BFR93P	SIEM	non	V _{GBO} =20B; I _G =50 MA; P _D =300 MBT; h ₂₁ =50200; f _T =5500 MFu	SOT23 SOD23	
GG	BRA143ECM	REN	Dono	V _{CC} =50 B; I _{CUT} =100 mA; P _D =150 mBT; h _{P1} >20; 4.7 к/4.7 к	S0T323,SC70	
GG	BRA143EMP	REN	Dono	Vcc=50 B; lour=100 mA; Pn=150 mBT; ho1>20; 4.7 k/4.7 k	SOT23,SOD23	
GH1	BCW69	ROHM	one	V _{CR0} =50 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =120260; f _T >150 МГц	SOT23,SOD23	
GH2	BCW70	ROHM	pnp	V _{Cen} =50 B; I _C = 100 мА; P _D =330 мВт; h ₂₁ =215500; f _T >150 МГц	SOT23.SOD23	
GK1	BCW71	ROHM	non	V _{CBO} -50B; I _C =100мA; P _D -350мBr; h ₂₁ -213500, гр 2150мПц V _{CBO} =50B; I _C =100мA; P _D =350мBr; h ₂₁ -120220; f _T >300МГц	SOT23,SOD23	100000000000000000000000000000000000000
GK2	BCW72	ROHM	non	V _{CB0} -50B; I _C =100мA; P _D -330мB1; h ₂₁ -120220, г _Т >300МГц V _{CB0} -50B; I _C =100мA; P _D -330мB1; h ₂₁ -200450; f _T >300МГц	SOT23,SOD23	C C C
GLP		MOT	-		SOT23,SOD23	
GLP	MMBT1010LT1 MSD1010T1	ETL	pnp	V _{CB0} =45B; I _C =100 mA; P _D =250 mBr; h ₂₁ >300		
-			pnp	V _{CB0} =45 B; I _C =100 MA; P _D =250 MBr; h ₂₁ >300	SOT346,SC59	
GMA	BFS17	ROHM	npn	V _{CB0} =25B; I _C =25MA; P _D =330MBT; h ₂₁ =25150; f _T >1000MF _U	SOT23,SOD23	and the second second
GR	2SA1455KR	ROHM	pnp	V _{CB0} =50 B; I _C =150 MA; P _D =200 MBT; h ₂₁ =180390; f _T >140 MFL	SOT346,SC59	7.007.000
GS	2SA1455KS	ROHM	pnp	V _{C80} =50 B; I _C = 150 mA; P _D =200 mBT; h ₂₁ =270560; f _T > 140 MFц	SOT346,SC59	127.50.00
GT1	BC846AT	CNTRL	npn	V _{CB0} =80 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =110220; f _T >100 МГц	SOT523	B·E·C
GT1	BCX17	ROHM	pnp	V _{CB0} =45B; I _C =500 мA; P ₀ =250 мВт; h ₂₁ =100600; f _T >100 МГц	SOT23,SOD23	
GT2	BC846BT	CNTRL	npn	V _{CB0} =80 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =200450; f _T >100 МГц	SOT523	B-E-C
GT2	BCX18	ROHM	pnp	V _{CB0} =30 B; I _C =500 мA; P _D =330 мВт; h ₂₁ =100600; f _T >100 МГц	SOT23,SOD23	
GT3	BC847AT	CNTRL	npn	V _{CB0} =50 B; I _C =100 мA; P _D =250 мBт; h ₂₁ =110220; f _T >100 МГц	SOT523	B-E-C
GT4	BC847BT	CNTRL	non	V _{CB0} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =200450; f _T >100 МГц	SOT523	B-E-C
GT5	BC847CT	CNTRL	npn	V _{CB0} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =420800; f _T >100 МГц	SOT523	B·E·C
GU1	BCX19	ROHM	npn	V_{C80} =50 B; I_C =500 mA; P_D =330 mBr; h_{21} =100600; f_T >200 M Γ_{LL}	SOT23,SOD23	B·E·C
GU2	BCX20	ROHM	npn	V_{CB0} =25B; I_C =500 MA; P_D =250 MBT; h_{21} =100600; f_T >100 M Γ_{II}	SOT23,SOD23	B·E·C
GV	1SV249	SANYO	pin×2	$V_R > 50 \text{ B}; I_F < 50 \text{ mA}; V_F (I_F = 50 \text{ mA}) = 0.92 \text{ B}; I_R < 0.1 \text{ mKA}$	SOT323,SC70	A1 · K2 · K1,A2
GV	1SV251	SANYO	pin×2	$V_R > 50 B$; $I_F < 50 mA$; $V_F (I_F = 50 mA) = 0.92 B$; $I_R < 0.1 mkA$	SOT23,SOD23	A1-K2-K1,A2
Н	MRF947BT1	MOT	npn	V _{CB0} =20 B; I _C =50 мA; P _D =188 мВт; h ₂₁ =100200; f _T =8 ГГц	SOT323,SC70	B·E·C
H02	DTC323TK	ROHM	Dnpn	V_{CB0} =30 B; I_{C} =600 mA; P_{D} =200 mB τ ; h_{21} =100600; f_{τ} >200 MF u_{c} R_{1} =2.2 kOm	SOT346,SC59	B-E-C
H02	DTC323TU	ROHM	Dnpn	V_{CB0} =30 B; I_C =600 mA; P_D =200 mBT; h_{21} =100600; f_T >200 MFu; R_1 =2.2 kOm	S0T323,SC70	B·E·C
H03	DTC343TK	ROHM	Dnpn	V_{CB0} =30 B; I_C =600 mA; P_0 =200 mBT; h_{21} =100600; f_T >200 MFu; R_1 =4.7 kOm	SOT346,SC59	B·E·C
H04	DTC314TK	ROHM	Dnpn	V _{CBO} =30 B; I _C =600 мA; P _D =200 мВт; h ₂₁ =100600; f _T >200 МГц; R ₁ =10 кОм	SOT346,SC59	B·E·C
H04	DTC314TU	ROHM	Dnpn	V _{CR0} =30 B; I _C =600 mA; P _D =200 mBT; h ₂₁ =100600; f _T >200 MFu; R ₁ =10 kOm	SOT323,SC70	B·E·C
H07	DTC363TK	ROHM	Dnpn	V_{CB0} =30 B; I_C =600 mA; P_D =200 mBT; h_{21} =100600; f_T >200 MFu; P_1 =6.8 x0 m	SOT346,SC59	B·E·C
H1	BCW69	ALLEG	pnp	V _{CB0} =50 B; I _{CB0} <100 нA; h ₂₁ =120260; V _{CRsstt} <0.3 B	SOT23,SOD23	B·E·C
H1	BCW69	CDIL	onp	V _{CD0} =50 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =120260; f _T >100 MFu	SOT23.SOD23	B·E·C
H1	BCW69	ZETEX	pnp	V _{CB0} =50 B; I _C =100 мА; P ₀ =330 мВт; h ₂₁ =120260; f _T >150 МГц	SOT23,SOD23	B·E·C
H1	MMBZ5241BT	DIODS	dz	V _A (I ₂₇ =20 mA)=10.4511.55 B; I _B < 2 mxA	SOT523	A·n.c.·K
H1	SST4416	SIL	nFET	V _{DS} =30B; P _D =350 мВт; I _{DSS} =515 мА; g _E =4.5 мСм; R _{DS(on)} =150 Ом	SOT23,SOD23	D·S·G
H10	KSC2755	SAMS	non	V _{GBO} =30 B; I _G =20 MA; P _D =150 MBT; h ₂₁ =70140; f _T >600 MFu	SOT23.SOD23	
H1p	BCW69	PHIL	pnp	V _{CR0} =50B; I _C =100 MA; P _D =250 MBT; h ₂₁ =120260; f _T >100 MFu	SOT23,SOD23	
HIR	KSC2755	SAMS	non	V _{CR0} =30 B; I _C =20 MA; P _D =150 MB; I _{D2} =4080; f _T >600 MFu	SOT23.SOD23	1000010000
H1t	BCW69	PHIL	ono	V _{CR0} =50B; I _C =100MA; P _D =250MBT; h ₂₁ =120260; f _T >100MFц	SOT23,SOD23	
		SAMS	non	V _{CR0} =30B; I _C =20MA; P _D =150MBT; h ₂₁ =120240; f _T >600MFu	SOT23,SOD23	0.0000000000000000000000000000000000000
HIY	KSC2755					

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
H2	BCW70	CDIL	pnp	V _{G80} =50 B; I _C =100 mA; P _D =250 mBt; h ₂₁ =215500; f _T >100 MFu	SOT23,SOD23	B·E·C
12	BCW70	ZETEX	qnq	V _{C80} = 50 B; I _C = 100 мA; P _D = 330 мВт; h ₂₁ = 215500; f _T > 150 МГц	SOT23,SOD23	B·E·C
12	MMBZ5242BT	DIODS	dz	V ₂ (I _{2T} =20 mA)=11.412.6B; I _B <1 mrA	SOT523	A·n.c.·K
121	2SJ463A	NEC	pMOS	V _{DS} =30 B; I _D =100 mA; P _D =150 mBT; R _{DSIon1} <23 Om	SOT323,SC70	G-S-D
H27	DTC363EK	ROHM	Dnpn	V_{C80} =30 B; I_{C} =600 xA; P_{D} =200 mBt; h_{21} >70; f_{T} >200 MFu; R_{1}/R_{2} =6.8/6.8 kOm	SOT346,SC59	B·E·C
127	DTC363EU	ROHM	Dnpn	V_{CR0} = 30 B; I_{c} = 600 MA; P_{0} = 200 MBT; h_{21} > 70; f_{T} > 200 MF I_{L} ; R_{1}/R_{2} = 6.8/6.8 KOM	SOT323,SC70	B·E·C
120	KSC2756	SAMS	npn	V_{C80} =20 B; I_C =30 mA; P_D =150 mBT; h_{21} =90180; f_T >850 MFu	SOT23,SOD23	B•E•C
1 2p	BCW70	PHIL	pnp	V_{CB0} =50 B; I_C =100 mA; P_D =250 mBt; h_{21} =215500; f_T >100 MFu	SOT23,SOD23	B-E-C
12R	KSC2756	SAMS	npn	V _{CB0} =20 B; I _C =30 мA; P _D =150 мВт; h ₂₁ =60120; f _T >850 МГц	SOT23,SOD23	B·E·C
H2t	BCW70	PHIL	pnp	V_{C80} =50 B; I_C =100 mA; P_D =250 mBr; h_{21} =215500; f_T >100 MFu	SOT23,SOD23	B-E-C
H2Y	KSC2756	SAMS	npn	V _{CB0} =20 B; I _C =30 мA; P _D =150 мВт; h ₂₁ =120240; f _T >850 МГц	SOT23,SOD23	B.E.C
13	2SA956H3	NEC	pnp	V _{C80} =60 B; I _C =100 мA; P _D =150 мВт; h ₂₁ =80130; fT>150 МГц	SOT23,SOD23	B·E·C
13	BCW89	CDIL	pnp	V _{CB0} =80 B; I _C =100 мA; P _D =250 мВт; h ₂₁ =120260; f _T >100 МГц	SOT23,SOD23	B·E·C
13	BCW89	ZETEX	pnp	V ₀₈₀ =80 B; I ₀ =100 мA; P ₀ =330 мВт; h ₂₁ =120260; f _T >150 МГц	SOT23,SOD23	B·E·C
13	KDV153	KEC	bd	V _B =20B; I _B =10 нА; С2 В=15пФ; С10В=5пФ; R _S <0.6 Ом	SOT23,SOD23	A·n.c.·K
13	MMBZ5243BT	DIODS	dz	V ₂ (I ₂₇ =9.5 mA)=12.3513.65B; I _B <0.5 mkA	SOT523	A·n.c.·K
131	BCW89R	PHIL	gng	V ₀₈₀ =60 B; I _C =100 мА; P _D =350 мВт; h ₂₁ =120260; f _T =150 МГц	SOT23,SOD23	E-B-C
130	KSC2757	SAMS	non	V _{G80} =30 B; I _C =50 mA; P _D =150 mBr; h ₂₁ =90180; f _T >1100 MFu	SOT23.SOD23	B-E-C
130	BCW89	PHIL	ono	V _{CRO} =80 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =120260; f _T =100 MFu	SOT23,SOD23	B·E·C
H3R	KSC2757R	SAMS	npn	V ₀₈₀ =30 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =60120; f ₁ >1100 МГц	SOT23,SOD23	B-E-C
13t	BCW89	PHIL	ono	V _{CRO} =80 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =120260; f _T =100 MFu	SOT23,SOD23	12000 120
13Y	KSC2757Y	SAMS	npn	V _{GR0} =30B; I _G =50 mA; P _D =150 mBT; h ₂₁ =120240; f _T >1100 MFu	SOT23.SOD23	
14	2SA956H4	NEC	ono	V _{CR0} =60 B; I _C =100 mA; P _D =150 mBr; h ₂₁ =110170; fT>150 MFц	SOT23,SOD23	
14	BCW69R	PHIL	ono	V _{CR0} =45 B; I _C =100 mA; P _D =350 mBr; h ₂₁ =120260; f _T =100 MFц	SOT23.SOD23	
14	BCW69R	ZETEX	ono	V _{CBC} =50 B; I _C =100 MA; P _D =330 MBr; h ₂₁ =120260; f _T >150 MFu	SOT23,SOD23	
14	SST5484	SIL	nFET	V _{DS} = 25 B; P _D = 350 MBT; I _{DSS} = 15 MA; g _E = 2 MCM	SOT23,SOD23	
H4Z	KSC2758	SAMS	npn	V _{CR0} =30 B; I _C =20 MA; P _D =150 MBT; h ₂₁ =60240; f _T >1000 MFu	SOT23,SOD23	200
15	2SA956H5	NEC	ono	V _{cR0} =60 B; I _c =100 мA; P _D =150 мBr; h ₂₁ =150240; fT>150 MΓц	SOT23,SOD23	100000 00
H5	BCW70R	PHIL	ono	V _{CR0} =45 B; I _C =100 MA; P _D =350 MBr; h ₂₁ =215500; f _T >100 MFu	SOT23.SOD23	
H5	BCW70R	ZETEX	ono	V _{CR0} =50 B; I _C =100 MA; P _D =330 MBT; h ₂₁ =215500; f _T >150 MF _U	SOT23,SOD23	
15	MMBZ5245BT	DIODS	dz	V ₂ (I ₂₇ =8.5 mA)=14.2515.75B; I _B <0.1 mrA	SOT523	A·n.c.·K
45	SST5485	SIL	nFET	V _{DS} =25 B; P _D =350 MBT; I _{DSS} =410 MA; Q _E =3.5 MCM	SOT23,SOD23	
150	KSC2223	SAMS	npn	V _{CR0} =30 B; I _C =20 mA; P _D =150 mBT; h ₂₁ =60120; f _T >600 MFų	SOT23,SOD23	
15R	KSC2223	SAMS	npn	V _{GB0} =30 B; I _G =20 MA; P _B =150 MBT; I ₂₁ =4080; I _T >600 MFц	SOT23,SOD23	707 0
15Y	KSC2223	SAMS	non	V _{C80} =30 B; I _C =20 мA; P _D =150 мВт; h ₂₁ =40au, i _T >600 МГц	SOT23,SOD23	
16	2SA956H6	NEC	ono	V _{CR0} =50 B; I _C =20 MA; P _D =150 MB1; I _{D1} =90160; I _T >500 MFL V _{CR0} =60 B; I _C =100 MA; P _D =150 MB1; I _{D1} =200320; IT>150 MFL	SOT23,SOD23	
16	BCW89R	ZETEX	ono	030	SOT23,SOD23	
16	BCW89R	PHIL		V _{CB0} =80 B; I _C =100 mA; P _D =330 mBr; h ₂₁ =120260; f _T >150 MFu	SOT23,SOD23	
16	SST5486	SIL	pnp	V _{CB0} =80 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =120260; f _T =100 MFц	SOT23,SOD23	1997
160		SAMS		V ₀₅ =25 B; P ₀ =350 MBT; I ₀₅₅ =820 MA; g _F =4 MCM	100 000 000 000 000 000	100000000000000000000000000000000000000
	KSC2759 KSC2759		npn	V _{CBO} =30 B; I _C =50 mA; P _D =150 mBT; h ₂₁ =60120; f _T >2000 MFu	SOT23,SOD23	
IGV	KSC2759	SAMS	npn	V _{CB0} =30 B; I _C =50 MA; P _D =150 MBT; h ₂₁ =4080; f _T >2000 MFц	SOT23,SOD23 SOT23,SOD23	
16Y			npn	V _{CB0} =30 B; I _C =50 mA; P _D =150 mBr; h ₂₁ =90180; f _T >2000 MFu		
171	BCF70R	PHIL	pnp	V _{CBO} =45B; I _C =100 мА; P _D =350 мВт; h ₂₁ =215500; f _T >100 МГц	SOT23,SOD23	
17p	BCF70	PHIL	pnp	V _{CB0} =50 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =215500; f _T >100 MFu	SOT23,SOD23	
18Z	KSC2734	SAMS	npn	V _{CB0} =20B; I _C =50 mA; P _D =150 mBT; h ₂₁ =20200; f _T >3500 MFu	SOT23,SOD23	100000000000000000000000000000000000000
19	1SS344	TOSH	shd	V _B >20 B; V _E (I _E =500 мА) < 0.55 B; I _R (V _R =20 B) < 20 мкА; С _Т < 120 пФ	SOT346,SC59	
19Z	KSC3120	SAMS	npn	V _{CB0} =30 B; I _C =50 mA; P _D =150 mBT; h ₂₁ =40200; f _T >2400 MF _U	SOT23,SOD23	
łA .	2SA1883	SANYO	pnp	V _{CB0} =15B; I _C =200 мA; P _D =150 мBт; h ₂₁ =50140; f _T >450 МГц	SOT416,SC75A	
łA.	2SC2804	TOSH	npn	V _{C80} +25 В; I _C +20 мА; Р _D +200 мВт; f _T > 900 МГц	SOT23,SOD23	
IA.	2SD1464	REN	npn	V_{CB0} =180 B; I_C =50 mA; P_D =1 BT; h_{21} =60120; f_T =140 M Γ_{II}	SOT23,SOD23	B·E·C





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
HAO	KSC3123	SAMS	npn	V _{CB0} =30 B; I _C =50 mA; P _D =150 mBT; h ₂₁ =90180; f _T >1400 MFu	SOT23,SOD23	B·E·C
HAR	KSC3123	SAMS	npn	V _{CBO} =30 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =60120; f _T >1400 МГц	SOT23,SOD23	B·E·C
HAY	KSC3123	SAMS	npn	V _{CB0} =30 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =120240; f _T >1400 МГц	SOT23,SOD23	B·E·C
НВ	2SD1464	REN	non	V _{CPD} =180B; I _C =50 MA; P _D =1BT; h ₂₁ =100200; f _T =140 MF _U	SOT23.SOD23	B-E-C
HBs	BFN22	SIEM	non	V _{сво} =250B; I _c =50мA; P _n =360мBт; h ₂₁ >50; f ₁ =100МГц	SOT23,SOD23	B-E-C
HC	2SC2733	REN	non	V _{CBO} =30 B; I _C =50 мA; P _D =150 мВт; h ₂₁ >60; f _T >600 МГц	SOT346.SC59	100000000000000000000000000000000000000
HC	2SC4463	REN	non	V _{CR0} =30 B; I _C =50 мA; P _D =100 мВт; h ₂₁ >60; f _T >600 МГц	SOT323,SC70	
HCs	BFN23	SIEM	pno	V _{CR0} =250 B; I _C =50 мA; P _D =360 мВт; h ₂₁ >50; f _T =100 МГц	SOT23,SOD23	
HE	2SC3906KE	ROHM	non	V _{CBD} =120B; I _C =50 MA; P _D =200 MBr; h ₂₁ =390820; f _T > 140 MFu	SOT346.SC59	
HE	2SC4102E	ROHM	non	V _{CB0} =120B; I _C =50 MA; P _D =200 MBT; h ₂₁ =390820; f _T >140 MFц	S0T323,SC70	
HG	BRC143ECM	REN	Dnpn	V _{CC} =50 B; I _{CH} =100 MA; P _D =200 MBT; h ₂₁ =350526; H7 H40 WHQ	SOT323,SC70	
HG	BRC143EMP	REN	Dnon	V _{CC} =50 B; I _{CUT} =100 MA; P _D =150 MB1; I _{P21} >20; 4.7 κ/4.7 κ	SOT23.SOD23	100000000000000000000000000000000000000
HP	2SA1036KP	ROHM	300	V _{CP0} =40 B; I _C =500 mA; P _D =100 mB; I _{D1} =20, 4.7 k)4.7 k	SOT346.SC59	5300000000
HP	55.000000000000000000000000000000000000	NUMM	pnp	000		200000000000000000000000000000000000000
	2SA1577P	DOLLI	pnp	V _{CB0} =40 B; I _C =500 MA; P _D =200 MBr; h ₂₁ =82180; f _T >200 MFц	S0T323,SC70	0.00.00
HQ	2SA1036KQ	ROHM	pnp	V _{CB0} =40 B; I _C =500 мA; P _D =200 мBτ; h ₂₁ =120270; f _T >200 MΓι ₄	SOT346,SC59	
HQ	2SA1577Q	ROHM	pnp	V _{CB0} =40 B; I _C =500 mA; P _D =200 mBr; h ₂₁ =120270; f _T >200 MFų	S0T323,SC70	
HQ	2SC3928Q	IDC	npn	V _{CB0} =50 B; I _C =200 MA; P _D =200 MBT; h ₂₁ =120270; f _T =200 MFU	SOT23,SOD23	
HR	2SA1035R	PAN	pnp	V _{CB0} =55B; I _C =100 мА; Р ₀ =200 мВт; h ₂₁ =180360; f₁=200 МГц	SOT23,SOD23	
HR	2SA1036KR	ROHM	pnp	V_{CB0} =40B; I_C =500 mA; P_D =200 mBT; h_{21} =180390; f_T >200 MF I_L	SOT346,SC59	T. (1771 - 77)
HR	2SA1531AR	PAN	pnp	V _{CBO} =55B; I _C =50 мA; P _D =150 мВт; h ₂₁ =180360; f _T =80 МГц	SOT323,SC70	122.50 120
HR	2SA1577R	ROHM	pnp	V_{CB0} =40B; I_C =500 mA; P_D =200 mBT; h_{21} =180390; f_T >200 M Γ_{II}	SOT323,SC70	
HR	2SC3906KR	ROHM	npn	V_{CB0} = 120 B; I_C = 50 mA; P_0 = 200 mBT; h_{21} = 180390; f_T > 140 M Γ II,	SOT346,SC59	B·E·C
HR	2SC3928R	IDC	npn	V_{CB0} = 50 B; I_C = 200 mA; P_D = 200 mBT; h_{21} = 180390; f_T = 200 MF χ	SOT23,SOD23	B-E-C
HR	2SC4102R	ROHM	non	V_{CB0} = 120 B; I_C =50 mA; P_D = 200 mBT; h_{21} = 180390; f_T > 140 M Γ_H	SOT323,SC70	B-E-C
HS	2SA1035S	PAN	pnp	V _{CB0} =55B;I _C =100 mA;P _D =200 mBt;h ₂₁ =260520; f _T =200 MFu	SOT23,SOD23	B·E·C
HS	2SA1531AS	PAN	pnp	V _{CB0} =55 B; I _C =50 MA; P _D =150 MBT; h ₂₁ =260520; f _T =80 MFu	SOT323,SC70	B·E·C
HS	2SC3906KS	ROHM	npn	V_{CB0} = 120 B; I_C =50 mA; P_D =200 mBT; h_{21} =270560; f_T >140 M Γ_{II}	SOT346,SC59	B·E·C
HS	2SC3928S	IDC	npn	V _{CB0} =50 B; I _C =200 мА; Р ₀ =200 мВт; h ₂₁ =270560; f ₁ =200 МГц	SOT23,SOD23	B·E·C
HS	2SC4102S	ROHM	npn	V _{CB0} =120 B; I _C =50 mA; P ₀ =200 mBT; h ₂₁ =270560; f _T >140 MFu	SOT323,SC70	B·E·C
HT	2SA1035T	PAN	pnp	V _{CR0} =55B; I _C =100 mA; P _D =200 mBt; h ₂₁ =360700; f _T =200 MFu	SOT23,SOD23	B·E·C
HT	2SA1531AT	PAN	prijo	V _{CBD} =55B; I _C =50 MA; P _D =150 MBT; h ₂₁ =360700; f ₁ =80 MFu	SOT323,SC70	B-E-C
нт	2SC3928T	IDC	non	V _{CRD} =50 B; I _C =200 мА; P _D =200 мВт; h ₂₁ =390820; f _T =200 МГц	SOT23,SOD23	B-E-C
ı	MRF947RT3	MOT	non	V _{CR0} =20B; I _C =50 mA; P _D =188 mBT; h ₂₁ >50; f _T =8000 MFu	SOT323,SC70	
10	SST110	SIL	nFET	V _{DS} =25B;P _D =350 MBT;I _{DSS} >10 MA;R _{DS(on)} <18 OM	SOT23.SOD23	1000000
18	SST108	SIL	nFET	V _{DS} = 25B; P _D = 350 MBT; I _{DSS} > 80 MA; R _{DS(on)} < 8 OM	SOT23,SOD23	
19	1SS336	TOSH	di×2	V _B <80 B; I _c <200 mA; V _c (I _c =200 mA)<1.2 B; I _B <0.5 mrA; t _{BB} <20 Hc	SOT346.SC59	
19	SST109	SIL	nFET	V _{DS} *25B;P _D *350 MBT; I _{DSS} >40 MA; R _{DSVool} <12 OM	SOT23.SOD23	
ID.	2SC3127	REN	non	V _{CRD} =20B; I _C =50 MA; P _D =150 MBT; f _T >3.5 ITu	SOT346.SC59	732.086 07
IE	2SC3722KE	ROHM	non	V _{CB0} =120 B; I _C =50 мA; Р _D =130 мВт; I _T > 3.511 Ц V _{CB0} =120 B; I _C =50 мA; Р _D =200 мВт; I _D =390820; f _T >140 МГц	SOT346,SC59	20000000
IGD	2SK1215D	REN	3			
	100000000000000000000000000000000000000			V _{DS} =20B; I _D =30 MA; P _D =100 MBT; g _F >8 MCM; I _{DSS} =48 MA	SOT323,SC70	
IGD	2SK360D	REN	nMOS	V _{DS} =20B; I _D =30 MA; P _D =150 MBT; g _F >8 MCM; I _{DSS} =48 MA	SOT23,SOD23	
IGE	2SK1215E	REN	nMOS	00	S0T323,SC70	
IGE	2SK360E	REN	nMOS	V _{DS} =20B; I _D =30 mA; P _D =150 mBr; g _F >8 mCm; I _{DSS} =610 mA	SOT23,SOD23	
IGF	2SK1215F	REN		V _{DS} =20B;I _D =30 MA;P _D =100 MBT; g _F >8 MCM; I _{DSS} =812 MA	SOT323,SC70	1350/2000/200
IGF	2SK360F	REN	nMOS	V _{DS} =20B; I _D =30 mA; P _D =150 mBT; g _F >8 mCm; I _{DSS} =812 mA	SOT23,SOD23	152227505
IJ	2SC3374	REN	npn	V _{CB0} =20B; I _C =20 мA; P _D =150 мВт; h ₂₁ =20200; f _T >400 МГц	SOT346,SC59	12 80 10
IL	2SC3493	REN	npn	V_{CB0} = 15B; I_C = 20 MA; P_D = 150 MBT; h_{21} = 30200; f_T > 700 M Γ_{II}	SOT346,SC59	
IL:	2SC4263	REN	npn	V_{CB0} = 15B; I_C = 20 MA; P_D = 100 MBT; h_{21} = 30200; f_T > 700 MFu	SOT323,SC70	B-E-C
10	KTA1298	KEC	pnp	V_{CB0} =35B; I_C =800 mA; P_D =200 mBT; h_{21} =100200; f_1 >120 MF μ	SOT23,SOD23	70000000
IP	2SC3793	REN	npn	V_{CB0} =20B; I_C =50 MA; P_D =150 MBT; h_{21} =50200; f_T >1.4FFu	SOT346,SC59	B·E·C
IP	2SC4262	REN	npn	V_{CB0} = 20 B; I_C = 50 MA; P_D = 100 MBT; h_{21} =50200; f_T > 1.4 Γ Γ U,	SOT323,SC70	B-E-C
IR	2SB792R	PAN	pnp	V _{CRD} = 150 B; I _C = 50 MA; P _D = 200 MBT; h ₂₁ = 130220; f _T = 200 MFц	SOT23,SOD23	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
IR	2SC3722KR	ROHM	npn	V _{CR0} =120 B; I _C =50 MA; P _D =200 MBT; h ₂₁ =180390; f _T >140 MFu	SOT346,SC59	B-E-C
R54	BAT54	IR	shd	V _B <30 B; I _E <200 мA; V _E (I _E =30 мA)<500 мB; C _D <10 пФ; t _{BB} <5 нс	SOT23,SOD23	
R54C	BAT54C	IR		V _B <30 B; I _E <200 мA; V _E (I _E =30 мA)<500 мB; C _D <10 пФ; t _{BB} <5 нс	SOT23,SOD23	A1-A2-K1,K2
R54S	BAT54S	IR	shd×2	V _B < 30 B; I _E < 200 mA; V _E (I _E =30 mA) < 500 mB; C _D < 10 mΦ; t _{DB} < 5 Hc	SOT23.SOD23	A1-K2-K1.A2
IRD	2SA1484D	HIT	pnp	V _{CR0} =90 B;I _C =100 mA; P _D =150 mBT; h ₂₁ =250500	SOT23,SOD23	
RE	2SA1484E	HIT	ono	V _{CB0} =90 B;I _C =100 mA; P _D =150 mB _T ; h ₂₁ =400800	SOT23.SOD23	100000000000000000000000000000000000000
IS	2SB792S	PAN	onp	V _{cpn} =150 B; I _c =50 мА; P _D =200 мВт; h ₂₁ =185330; f _T =200 МГц	SOT23,SOD23	B-E-C
IS	2SC3513	REN	non	V _{CR0} =15 B; I _C =50 mA; P _D =150 mBr; h ₂₁ =50250; f _T >4.5 ГГц	SOT346.SC59	
IS	2SC3722KS	ROHM	npn	V _{CB0} =120 B; I _C =50 мА; P _D =200 мВт; h ₂₁ =270560; f _T >140 МГц	SOT346.SC59	
IS	2SC4537	REN	ngn	V _{CBB} =15 B;I _C =50 mA; P _D =100 mBr; h ₂₁ =50250; f _T >4.5 ГГц	SOT323.SC70	
T	2SB792T	PAN	onp	V _{CRN} =150 B; I _C =50 мА; P _D =200 мВт; h ₂₁ =260450; f _T =200 МГц	SOT23,SOD23	
Υ	KTA1298	KEC	gng	V _{CBO} =35 B; I _C =800 mA; P _D =200 mBr; h ₂₁ =160320; f _T >120 MFų	SOT23,SOD23	17503200000
JO	HSMS2840	HP	shd	V _{BR} > 25 B; V _E (I _E =30 mA) < 0.7 B; I _B (V _B =1B) < 100 μA; C _T <1.0 πΦ; R _D =12 O _M	SOT23,SOD23	120000120
J01	SO2906R	SGS	ono	V _{CBD} =40 B; I _C =150 mA; P _D =300 mB; h ₂₁ =40120; f _T >200 MFu	SOT23,SOD23	
J03	SO2907AR	SGS	1 1		SOT23,SOD23	55-55
J05		SGS	pnp	V _{CB0} =60 B; I _C =150 MA; P _D =300 MB; h ₂₁ =100300; f _T >200 MFų	SOT23,SOD23	
_	SO2907R	_	pnp	V _{GB0} =40 B; I _G =200 MA; P _D =300 MBT; h ₂₁ =100300; f _T >200 MFц		
J06	SO2894R	SGS	pnp	V _{CB0} =12 B; I _C =200 мА; P _D =300 мВт; h ₂₁ =40150; f _T >400 МГц	SOT23,SOD23	
J1	BSS138L	MOT	nMOS	V _{DS} =50 B; I _D =200 mA; P _D =360 mBT; g _F =120 mCm; R _{DS(on)} =6 Om	SOT23,SOD23	0.0000 00
J1	HSMS2841	HP	shd	$V_{BR} > 25 \text{ B; } V_f (I_F = 30 \text{ mA}) < 0.7 \text{ B; } I_R (V_R = 1 \text{ B}) < 100 \text{ mA; } C_T < 1.0 \text{ m}\Phi; R_D = 12 \text{ OM}$	SOT23,SOD23	100000000000000000000000000000000000000
J1	MMBZ5246BT	DIODS	dz	V ₂ (I _{ZT} =7.8 mA)=15.216.8 B; I _R <0.1 mrA	10.00.00.000	A·n.c.·K
J12	SO2906AR	SGS	pnp	V_{CB0} =60 B; I_C =150 мA; P_D =300 мBт; h_{21} =40120; f_T >200 МГц	SOT23,SOD23	
J1A	ZC830A	ZETEX	ASL	V _R <25 B; C _{2B} =10±10% πΦ; C _{2B} /C _{20B} =4.56; Q>300	SOT23,SOD23	
J1B	ZC830B	ZETEX	var	$V_B < 25 B; C_{2B} = 10 \pm 5\% n\Phi; C_{2B} / C_{20B} = 4.56; Q > 300$	SOT23,SOD23	A·n.c.·K
J10	KSA1298	SAMS	pnp	V_{CB0} =30 B; I_C =800 MA; P_D =200 MBT; h_{21} =100200; f_T >120 MF $_{4}$	SOT23,SOD23	B-E-C
J1S	ZC830	ZETEX	var	V _R <25 B; C _{2B} =10 ± 20% nΦ; C _{2B} /C _{20B} =4.56; Q>300	SOT23,SOD23	A·n.c.·K
J1Y	KSA1298	SAMS	pnp	V_{CB0} =30 B; I_C =800 MA; P_D =200 MBT; h_{21} =160320; f_T >120 MFu	SOT23,SOD23	B-E-C
J2A	ZC833A	ZETEX	var	V _R <25 B; C _{2B} =33 ± 10% nФ; C _{2B} /C _{20B} =56.5; Q>200	SOT23,SOD23	A·n.c.·K
J2B	ZC833B	ZETEX	var -	V _R <25 B, C _{2B} =33±5%nΦ;C _{2B} /C _{20B} =56.5; Q>200	SOT23,SOD23	A·n.c.·K
J2S	ZC833	ZETEX	var	V _B <25 B; C _{2B} =33 ± 20% nФ; C _{2B} /C _{20B} =56.5; Q>200	SOT23,SOD23	A·n.c.·K
J3	MMBZ5248BT	DIODS	dz	V ₂ (I _{ZT} =7.0 mA)=17.118.9 B; I _B < 0.1 mkA	SOT523	A·n.c.·K
J32	S05400R	SGS	pnp	V _{CB0} =130 B; I _C =600 мА; P _D =200 мВт; h ₂₁ =40180; f _T >100 МГц	SOT23,SOD23	E-B-C
J33	S05401R	SGS	ono	V _{CB0} =160 B; I _C =600 мА; P _D =200 мВт; h ₂₁ =60240; f _T >100 МГц	SOT23,SOD23	E-B-C
J39	SO692R	SGS	ono	V _{сво} =300 B; I _c =100 мА; P _n =310 мВт; h ₂₁ >40; f ₇ >50 МГц	SOT23,SOD23	E-B-C
J3A	ZC831A	ZETEX	var	V _B <25B; C _{2B} =15±10% πΦ; C _{2B} /C _{20B} =4.56; Q>300	SOT23,SOD23	A·n.c.·K
J3B	ZC831B	ZETEX	var	V _B <25 B, C _{2B} =15±5%nΦ;C _{2B} /C _{20B} =4.56; Q>300	SOT23,SOD23	/
J3D	MSB81T1	MOT	ono	f ₁ =0.6 ΓΓ ₄	SOT23.SOD23	
J3S	ZC831	ZETEX	var	V _B <25 B; C _{2B} =15±20% πΦ; C _{2B} /C _{20B} =4.56; Q>300	SOT23,SOD23	Sa transcriptor
J4A	MBV109T1	MOT	var	V _B >30 B _i I _F =200 mA; C _{3B} =2632 nΦ; C _{3B} /C _{25B} =5.06.5	S0T323.SC70	Section of the sectio
J4A	ZC832A	ZETEX	var	V _B <25 B; C _{2B} =22±10% nΦ; C _{2B} /C _{20B} =56.5; Q>200	SOT23,SOD23	20,000,000,000
J4B	ZC832B	ZETEX	var	V _R <25 B; C _{2B} =22±5%πΦ; C _{2B} /C _{20B} =56.5; Q>200	SOT23,SOD23	
J4S	ZC832	ZETEX	ASIL	V _R <25 B; C _{2B} =22±20% пФ; C _{2B} /C _{20B} =56.5; Q>200	SOT23,SOD23	
J5	MMBZ5250BT	DIODS	dz	V ₂ (I ₂₁ =6.2 mA)=19.021.0 B; I _B <01 mkA	SOT523	A·n.c.·K
J5A	ZC834A	ZETEX	var	V _R <25 B, C _{2B} =47 ± 10% nΦ; C _{2B} /C _{21B} =56.5; Q>200	SOT23,SOD23	
J5B	ZC834B	ZETEX	var	V _B <25 B; C _{2B} =47 ± 10% (1Φ; C _{2B} /C _{20B} =56.5; Q>200 V _B <25 B; C _{2B} =47 ± 5% (1Φ; C _{2B} /C _{20B} =56.5; Q>200	SOT23,SOD23	1,000 000 000 000
JSS JSS	ZC834B ZC834			$V_B < 25 B; C_{2B} = 47 \pm 5\% \Pi \Psi; C_{2B}/C_{20B} = 56.5; Q > 200$ $V_B < 25 B; C_{2B} = 47 \pm 20\% \Pi \Phi; C_{2B}/C_{20B} = 56.5; Q > 200$	SOT23,SOD23	
J6	M1MA174	ZETEX	var		S0T323,S0D23	
		100000	di	V _R <100 B; I _F <200 mA; V _F (I _F =10 mA)<1 B; t _{RB} <4 Hc		
J6A	ZC835A	ZETEX	var	V ₈ <25 B; C _{2B} =68±10% πΦ; C _{2B} /C _{20B} =56.5; Q>100	SOT23,SOD23	
J6B	ZC835B	ZETEX	var	V _R <25 B; C _{2B} =68±5%nΦ; C _{2B} /C _{20B} =56.5; Q>100	SOT23,SOD23	
J6S	ZC835	ZETEX	var	V _R <25 B; C _{2B} =68±20% πΦ; C _{2B} /C _{20B} =56.5; Q>100	SOT23,SOD23	
J7A	ZC836A	ZETEX	var	V _R <25 B; C _{2B} =100 ± 10% nΦ; C _{2B} /C _{20B} =56.5; Q > 100	SOT23,SOD23	N. C.
J7B	ZC836B	ZETEX	var	V _R <25 B; C _{2B} =100±5% пФ; C _{2B} /C _{20B} =56.5; Q>100	SOT23,SOD23	
J7S	ZC836	ZETEX	var	V _R <25 B; C _{2B} = 100 ± 20% ηΦ; C _{2B} /C _{20B} =56.5; Q > 100	SOT23,SOD23	A·n.c.·K





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
J8	BCX71JR	ZETEX	pnp	V _{CB0} =45B; I _C =200 мА; P _D =330 мВт; h ₂₁ =250460; f _T > 180 МГц	SOT23,SOD23	B-E-C
18	BCX71JR	PHIL	pnp	V _{CBO} =45B; I _C =200 мА; P _D =250 мВт; h ₂₁ =250460; f _T >100 МГц	SOT23,SOD23	C·B·E
J9	1SS337	TOSH	di×2	VB < 80 B; IE < 200 MA; VE (IE = 200 MA) < 1.2 B; IB < 0.5 MKA; TBB < 20 HC	SOT346,SC59	A1 • A2 • K1, K2
J9A	ZC829A	ZETEX	ASI.	V _B <25B; I _F <200 мА; I _B <0.02 мкА; С _{2B} =7.389.02 пФ; С _{2B} /С _{20B} =4.35.8	SOT23,SOD23	A+n.c.+K
J9B	ZC829B	ZETEX	var	V ₈ <25B; I _F <200 мА; I ₈ <0.02 мкА; С _{2B} =7.798.61 пФ; С _{2B} /С _{20B} =4.35.8	SOT23,SOD23	A+n.c.+K
JA	BAV70W	WTE	di×2	V _B <75B; I _F <300 мА; V _F (I _F : 50 мА)<1.0B; С _D <2 пФ; t _{PB} <6 нс	SOT323,SC70	A1-A2-K1,K2
JA	BAV74	ALLEG	di×2	$\begin{array}{l} I_{F}\!<\!70\text{MA};V_{BR}\!>\!50B;V_{F}\!(I_{F}\!=\!100\text{MA})\!<\!1.0B;I_{R}\!<\!100\text{HA};I_{RR}\!<\!4.0\text{Hc};\\ C_{D}\!<\!2.0\text{n}\Phi \end{array}$	S0T23,S0D23	A1+A2+K1,K2
JA	BAV74	ZETEX	di×2	$V_B \le 50 B$; $I_F \le 150 \text{ mA}$; $V_F (I_F = 100 \text{ mA}) \le 1.0 B$; $I_B \le 0.1 \text{ mKA}$; $C_D \le 2 \text{ n}\Phi$; $t_{BB} \le 4 \text{ HC}$	SOT23,SOD23	A1-A2-K1,K2
JA	BAV74	Nat	di×2	V _B <50 B; I _E <200 mA; V _E (I _E =100 mA)<1 B; C _D <2 nΦ; t _{BB} <4 hc	SOT23,SOD23	A1-A2-K1,K2
JAp	BAV74	PHIL	di×2	V _B <50B; I _E <215мA; V _E (I _E =100мA)<1.0B; C _D <2.0пФ; t _{BB} <4нс	SOT23,SOD23	A1+A2+K1,K2
JAs	BAV74	SIEM	di×2	$V_{\rm H} < 50 \rm B; l_F < 200 \rm mA; V_{\rm H} (l_F = 100 \rm mA) < 1.0 \rm B; l_H < 0.1 mrA; C_0 < 2.0 n\Phi; l_{\rm HM} < 4 \rm mc$	S0T23,S0D23	A1+A2+K1,K2
JB	BAR74	ZETEX	di	V_R < 50 B; I_F < 150 mA; V_R (I_F = 100 mA) < 1.0 B; I_R < 0.1 mrA; C_D < 2.0 πΦ; I_{RR} < 4 HC	SOT23,SOD23	A•n.c.•K
JC	2SC2735	REN	npn	V _{CB0} =30 B; I _C =50 mA; P _D =150 mBT; h ₂₁ >40; f _T >600 MTu	SOT346,SC59	B·E·C
JC	2SC4265	REN	npn	V _{CB0} =30 B; I _C =50 MA; P _D =100 MBT; h ₂₁ >40; f _T >600 MFu	SOT323,SC70	B·E·C
JC	BAL74	ZETEX	di	V_{B} < 50 B; I_{E} < 150 mA; V_{F} (I_{E} = 100 mA) < 1.0 B; I_{B} < 0.1 mrA; C_{D} < 2 $\pi\Phi$; t_{BB} < 4 HC	SOT23,SOD23	n.c.+A+K
JC	BAL74W	PHIL	fd	V _B <75B; I _F <175 MA; V _F (I _F =50 MA)<1.0B; C _D <1.5 πΦ; t _{BB} <4 Hc	SOT323,SC70	n.c.+A+K
JC	BAW56W	PANJIT	di×2	V _B <75B; I _F <150 mA; V _F (I _F =10 mA)<1B; C _D <4 nΦ; t _{PB} <4 mc	SOT323,SC70	K1-K2-A1,A2
JCp	BAL74	PHIL	fd	V _B <50B; I _F <215 мA; V _F (I _F =50 мA)<1.0B; C _D <2 пФ; t _{RB} <4 нс	SOT23,SOD23	n.c.+A+K
JCs	BAL74	INF	di	$V_B \le 50 B_1 I_F \le 250 \text{ mA}; V_F (I_F = 100 \text{ mA}) \le 1.0 B_1 I_B \le 0.1 \text{ m/A}; C_D \le 2 \text{ n/D}; t_{BB} \le 4 \text{ HC}$	SOT23,SOD23	n.c.+A+K
JD	BAW56	VISH	di×2	$V_{\rm H}$ <70 В; $I_{\rm F}$ <300 мА; $V_{\rm F}$ ($I_{\rm F}$ = 150 мА) < 1.25 В; $I_{\rm H}$ <5.0 мкА; $C_{\rm D}$ <4.0 п Φ ; $I_{\rm BR}$ <6 нс	SOT23,SOD23	K1•K2•A1,A2
JD	BAW56T	DIODS	di×2	V _B <85 B; I _F <155 mA; V _F (I _F =150 mA)<1.25 B; I _B <2 mkA; t _{BB} <4 hc	SOT523	K1 · K2 · A1,A2
JE	BAV99	VISH	di×2	$V_R < 70 B_i I_F < 300 \text{mA}; V_R (I_F = 150 \text{mA}) < 1.25 B_i I_R < 5.0 \text{mkA}; C_0 < 4.0 \text{n} \Phi; t_{RR} < 6 \text{Hz}$	SOT23,SOD23	A1•K2•K1,A2
JE	BAV99	GS	di×2	$V_R \le 70 B$; $I_F \le 250 \text{ mA}$; $V_F (I_F = 150 \text{ mA}) \le 1.25 B$; $I_R \le 2 \text{ mkA}$; $I_{RR} \le 4 \text{ Hc}$	SOT23,SOD23	A1-K2-K1,A2
JE	BAV99	TSC	di×2	V_R <75B; I_F <215 mA; V_R (I_F * 150 mA)<1.25 B; I_R <2 mkA; t_{RR} <4 Hc	SOT23,SOD23	A1+K2+K1,A2
JE	BAV99T	DIODS	di×2	V _R <85 B; I _F <155 mA; V _F (I _F =150 mA)<1.25 B; I _R <2 mkA; t _{RR} <4 hc	SOT523	A1 · K2 · K1,A2
JF	BAL99	VISH	di	$V_{R}\!<\!70B;I_{F}\!<\!250\text{ mA};V_{R}\!\{I_{F}\!\!:\!50\text{ mA}\}\!<\!1.0B;I_{R}\!<\!2.5\text{ mkA};C_{D}\!<\!1.5\text{ n}\Phi;t_{RR}\!<\!6\text{ hc}$	SOT23,SOD23	n.c.•K•A
JF	BAL99	GS	di	$V_R \le 70 B_1 I_F \le 250 \text{ mA}; V_F (I_F = 150 \text{ mA}) \le 1.25 B_1 I_R \le 2 \text{ mxA}; t_{BR} \le 4 \text{ Hz}$	SOT23,SOD23	n.c.•K•A
JF	BAL99W	PHIL	di	$V_R < 70B$; $I_F < 150 \text{ mA}$; $V_R (I_F = 50 \text{ mA}) < 1.0B$; $C_D < 1.5 \text{ m}\Phi$; $t_{RR} < 4 \text{ Hz}$	SOT323,SC70	n.c.•K•A
JFp	BAL99	PHIL	di	V _R <70B; I _F <250мA; V _F (I _F =50мA)<1.0B; C _D <1.5пФ; t _{RR} <6нс	SOT23,SOD23	n.c.+K+A
JFs	BAL99	INF	di	$V_R < 70B$; $I_F < 250$ mA; $V_F (I_F = 50$ mA) $< 1.0B$; $I_R < 2.5$ mKA; $C_D < 1.5$ n Φ ; $t_{RR} < 6$ Hz	SOT23,SOD23	n.c. · K·A
JG	BAV99	WTE	di×2	$V_R < 75 B$; $I_F < 300 \text{ mA}$; $V_F (I_{F^{\pm}} 150 \text{ mA}) < 1.25 B$; $I_R < 2 \text{ mkA}$; $t_{BR} < 4 \text{ Hc}$	SOT23,SOD23	A1·K2·K1,A2
JG	BAV99	PANJIT	di×2	V _B <75B;I _F <150 mA; V _E (I _F =10 mA)<1B; t _{RB} <4 hc	SOT23,SOD23	A1 · K2 · K1,A2
JG	BRA123ECM	REN	Dpnp	V_{CC} =50 B; I_{DUT} =100 mA; P_D =150 mBT; h_{21} >20; 2.2 k/2.2 k	SOT323,SC70	1,000,000,000
JG	BRA123EMP	REN	Dpnp	V _{CC} =50 B; I _{OUT} =100 mA; P _D =150 mB+; h ₂₁ >20; 2.2 к/2.2 к	SOT23,SOD23	B·E·C
JGs	BAR99	SIEM	di	$V_R < 70 B_1 I_F < 250 \text{mA}; V_F (I_F = 50 \text{mA}) < 1.0 B_1 I_R < 2.5 \text{mKA}; C_0 < 1.5 \text{n} \Phi; t_{RR} < 6 \text{Hz}$	SOT23,SOD23	K·n.c.·A
JID	2SA1566D	REN	pnp	V _{CB0} =120 B; I _C =100 mA; P _D =150 mBt; h ₂₁ =250500	SOT23,SOD23	B-E-C
JIE	2SA1566E	REN	pnp	V _{CB0} = 120 B; I _C = 100 mA; P _D = 150 mBt; h ₂₁ =400800	SOT23,SOD23	B-E-C
IJ	BAV70	VISH	di×2	$V_R <$ 70 В; $I_F <$ 300 мА; $V_R (I_F = 150$ мА) $<$ 1.25 В; $I_R <$ 5.0 мкА; $C_D <$ 4.0 п Φ ; $I_{RR} <$ 6 нс	SOT23,SOD23	A1 • A2 • K1, K2
JJ	BAV70T	DIODS	di×2	V _R <85 B; I _F <155 mA; V _F (I _F =150 mA)<1.25 B; I _R <2 mxA; I _{FR} <4 HC	SOT523	A1+A2+K1,K2
JL	MRF949T1	MOT	npn	V _{CB0} =20B; I _C =50 MA; P _D =144 MBT; h ₂₁ >50; f _T =9 ITU	SOT323,SC70	B·E·C
JM	2SC2059KM	ROHM	npn	V _{CBO} =25B; I _C =20 мA; P _D =150 мВт; h ₂₁ =3982; f _T >500 МГц	SOT346,SC59	B·E·C
JM	2SC4099M	ROHM	npn	V _{CB0} =25B; I _C =20 мA; P _D =150 мВт; h ₂₁ =3982; f _T >500 МГц	SOT323,SC70	B·E·C
JM	2SC4649	ROHM	npn	V _{CB0} =25B; I _C =20 мA; P _D =150 мВт; h ₂₁ =3982; f _T >500 МГц	SOT416,SC75A	B·E·C
JN	2SC2059KN	ROHM	npn	V _{CB0} =25B; I _C =20мA; P _D =150 мВт; h ₂₁ =56120; f _T >500 МГц	SOT346,SC59	B-E-C
JN	2SC4099N	ROHM	npn	V _{CB0} =25B; I _C =20 мA; P _D =150 мВт; h ₂₁ =56120; f ₁ >500 МГц	SOT323,SC70	B-E-C
JN	2SC4649	ROHM	npn	V _{GB0} =25B; I _C =20 мА; P _D =150 мВт; h ₂₁ =56120; f _T >500 МГц	SOT416,SC75A	B·E·C
JP	2SC2059KP	ROHM	non	V _{CB0} =25B; I _C =20 MA; P _D =150 MBT; h ₂₁ =82180; f _T >500 MFu	SOT346.SC59	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
JP	2SC4099P	ROHM	npn	V _{CB0} = 25 B; I _C = 20 мА; P ₀ = 150 мВт; h ₂₁ = 82180; f ₁ > 500 МГц	SOT323,SC70	B-E-C
JP	2SC4649	ROHM	npn	V _{GB0} =25 B; I _G =20 мА; Р ₀ =150 мВт; h ₂₁ =82180; f _T >500 МГц	SOT416,SC75A	B·E·C
JPp	BAS19	PHIL	fd	$V_B < 100 \text{ B; } I_E < 200 \text{ mA; } V_E (I_E = 100 \text{ mA}) < 1.0 \text{ B; } C_0 < 5 \text{ m} \Phi; t_{BB} < 50 \text{ Hz}$	SOT23,SOD23	A•n.c.•K
JPs	BAS19	INF	di	V_B < 100 B; I_F < 250 MA; V_E (I_F = 100 MA) < 1.0 B; I_B < 0.1 MKA; C_D < 5.0 nΦ; I_{BB} < 5.0 HC	SOT23,SOD23	A•n.c.•K
JRp	BAS20	PHIL	fd	V _R < 150 B; I _F < 200 мА; V _F (I _F = 100 мА) < 1.0 B; C _D < 5 пФ; t _{RR} < 50 нс	SOT23,SOD23	A·n.c.·K
JRs	BAS20	INF	di	V_R < 150 B; I_F < 250 κA; V_R (I_F = 100 κA) < 1.0 B; I_R < 0.1 κκA; C_O < 5.0 πΦ; I_{RR} < 50 HC	SOT23,SOD23	1: 9/0.00011 (ESS
JS	BAS21	JGD	di	V_B < 200 B; I_F < 200 мA; V_B (I_F = 100 мA) < 1.0 B; I_B < 0.1 мKA; C_O < 1.5 πΦ; I_{BB} < 50 Hc	SOT23,SOD23	137.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.1.
JS3	2SA1857	SANYO	pnp	V_{CB0} =15 B; I_C =50 mA; P_D =150 mBT; h_{21} =60120; f_T >750 M Γ_{II}	SOT323,SC70	T077 33
JS4	2SA1857	SANYO	pnp	V_{CB0} = 15 B; I_C = 50 mA; P_D = 150 mBT; h_{21} =90180; f_T >750 MFu	SOT323,SC70	B-E-C
JS5	2SA1857	SANYO	pnp	V_{CB0} =15 B; I_C =50 mA; P_D =150 mBt; h_{21} =135270; f_T >750 MFu,	SOT323,SC70	B·E·C
JSp	BAS21	PHIL	fd	$V_R < 200 \text{ B; } I_E < 200 \text{ MA; } V_E (I_E = 100 \text{ MA}) < 1.0 \text{ B; } C_0 < 5 \text{ m}\Phi ; t_{RR} < 50 \text{ Hc}$	SOT23,SOD23	A·n.c.·K
JSs	BAS21	INF	di	V_R < 200 B; I_F < 250 MA; V_R (I_F = 100 MA) < 1.0 B; I_R < 0.1 MKA; C_D < 5.0 nΦ; t_{RR} < 5.0 HC	SOT23,SOD23	
JV	1SV263	SANYO	pin	V _R >50 B; I _F <50 mA; V _F (I _F =50 mA)<0.95 B; I _R <0.1 m kA	SOT323,SC70	A·n.c.·K
JV	1SV266	SANYO	pin	V _B >50 B; I _E <50 mA; V _E (I _E =50 mA)=0.91 B; I _B <0.1 mrA	SOT23,SOD23	A•n.c.•K
JVp	BAS116	PHIL	dl	$V_R < 75B; I_F < 215 \text{ MA}; V_F (I_F = 10 \text{ MA}) \le 1.0B; I_R (V_R = 75B) \le 5 \text{ HA}; C_0 \le 2 \text{ n}\Phi; t_{RR} \le 3000 \text{ Hz}$	SOT23,SOD23	A•n.c.•K
JVs	BAS116	SIEM	dl	V_B <75 B; I_F <250 mA; V_F (I_F =50 mA)<1.1B; I_B <5.0 m KA; C_D <2.0 n Φ ; t_{BB} <3000 Hc	SOT23,SOD23	A•n.c.•K
JX	BAV170	MOT	dl×2	V_B < 80 B; I_F < 200 mA; V_F (I_F = 150 mA) < 1.25 B; I_B < 0.005 mrA; C_0 < 2.0 m Φ ; I_{BB} < 3000 Hc	SOT23,SOD23	A1+A2+K1,K2
JXp	BAV170	PHIL	dl×2	$V_B < 75B; I_F < 215 \text{ MA}; V_F (I_F = 10 \text{ MA}) < 1.0B; I_R (V_B = 75B) < 5 \text{ HA}; C_0 < 2 \text{ n}\Phi; t_{BB} < 3000 \text{ Hz}$	SOT23,SOD23	A1+A2+K1,K2
JXs	BAV170	INF	dl×2	$\begin{array}{l} V_{B}\!<\!80B;I_{F}\!<\!200\text{mA};V_{F}\!(I_{F}\!=\!150\text{mA})\!<\!1.25B;I_{B}\!<\!0.005\text{mxA};C_{0}\!<\!2.0\text{n\Phi};\\ t_{BB}\!<\!3000\text{Hz} \end{array}$	SOT23,SOD23	A1+A2+K1,K2
JXt	BAV170	PHIL	dl×2	V_R <75B; I_F <215mA; V_F (I_F =10mA)<1.0B; I_R (V_R =75B)<5hA; C_0 <2n Φ ; I_{RR} <3000hc	SOT23,SOD23	A1+A2+K1,K2
JYp	BAV199	PHIL	dl×2	$V_B < 75B; I_F < 160 \text{ mA; } V_F I_F = 10 \text{ mA}) < 1.0B; I_F I_F = 75B} < 5 \text{ HA; } C_0 < 2 \text{ n}\Phi; \\ I_{BB} < 3000 \text{ Hc}$	SOT23,SOD23	A1 • K2 • K1,A2
JYs	BAV199	INF	dl×2	V_B < 80 B; I_F < 200 мА; V_F (I_F = 150 мА) < 1.25 B; I_B < 0.005 мкА; C_0 = 2.0 п Φ ; t_{BB} < 1500 нс	SOT23,SOD23	A1-K2-K1,A2
JYs	BAV199F	INF	dl×2	V_R < 80 B; I_r < 200 mA; V_r (I_r = 150 mA) < 1.25 B; I_R < 0.005 mrA; C_0 = 2.0 n Φ ; I_{RR} < 1500 Hc	TSFP-3,VESM	A1 • K2 • K1,A2
JZ p	BAW156	PHIL	dl×2	$V_8 < 75B; I_e < 160 \text{ mA; } V_e (I_e = 10 \text{ mA}) < 1.0B; I_e (V_8 = 75B) < 5 \text{ HA; } C_0 < 3 \text{ n}\Phi; \\ t_{BB} < 3000 \text{ Hz}$	SOT23,SOD23	K1 · K2 · A1, A2
JZs	BAW156	SIEM	dl×2	V_B < 70 B; I_F < 200 mA; V_F (I_F = 150 mA) < 1.25 B; I_B < 0.005 mκA; C_0 < 2.0 πΦ; t_{BB} < 3000 Hc	SOT23,SOD23	K1-K2-A1,A2
K	MRF917T1	MOT	npn	V _{CB0} =20 B; I _C =60 мA; P ₀ =222 мВт; h ₂₁ =40200; f ₇ =6 ГГц	SOT323,SC70	B-E-C
K0	HSMP3830	HP	pin	I _F <1A;V _{BR} >200 B; R _S <1.5 Ом; С _О <0.3 пФ	SOT23,SOD23	A·n.c.·K
K1	BCW71	ALLEG	npn	V _{CB0} =50 B; I _{CB0} <100 HA; h ₂₁ =110220; V _{CE(sat)} <0.25 B	SOT23,SOD23	
K1	BCW71	CDIL	npn	V_{CB0} =50 B; I_C = 100 mA; P_D =250 mBT; h_{21} =110220; f_T >100 MF $_{\rm II}$	SOT23,SOD23	B-E-C
K1	BCW71	SAMS	npn	V_{CB0} =50 B; I_C = 100 mA; P_D =350 mBT; h_{21} =120220; f_T >300 MF $_{\rm II}$	SOT23,SOD23	B-E-C
K1	BCW71	ZETEX	npn	V_{CB0} =50 B; I_C =100 mA; P_D =330 mBr; h_{21} =110220; f_T >300 M Γ_U	SOT23,SOD23	B-E-C
K1	HSMP3831	HP	pin	$I_F \le 1A; V_{BR} \ge 200 B; R_S \le 1.5 \text{ DM}; C_D \le 0.3 \text{ n}\Phi$	SOT23,SOD23	n.c. ·A·K
K1	MMBZ5251BT	DIODS	dz	V ₂ (I _{ZT} =5.6 mA)=20.923.1 B; I _R < 0.1 mrA	SOT523	A·n.c.·K
K1	VN 10KT	SIL	nMOS	V _{DS} =60 B; I _D =310 мA; P _D =1000 мВт; g _F =100 мСм; R _{DS(on)} =7.5 Ом	SOT23,SOD23	
K14	DTA114GE	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBT; h_{21} >30; f_T >250 M Γ_U ; R_2 =10 kOm	SOT416,SC75A	
K14	DTA114GKA	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBT; h_{21} >30; f_T >250 MFu; R_2 =10 kOm	SOT346,SC59	
K14	DTA114GUA	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBt; h_{21} >30; f_T >250 MFu; R_2 =10 kOm	SOT323,SC70	B·E·C
K15	DTA124GKA	ROHM	Dpnp	V _{GB0} =50 B; I _C =100 mA; P _D =200 mBt; h ₂₁ >56; f _T >250 MFu; R ₂ =22 kOm	SOT346,SC59	B.E.C
K15	DTA124GUA	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBT; h_{21} >56; f_T >250 MFu; R_2 =22 kOm	SOT323,SC70	B-E-C
K16	DTA144GKA	ROHM	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBT; h_{21} >68; f_T >250 MFu; R_2 =47 kOm	SOT346,SC59	B·E·C
K16	DTA144GUA	ROHM	Dono	V _{GB0} =50 B; I _G =100 мА; P _D =200 мВт; h ₂₁ >68; f _T >250 МГц; R ₂ =47 кОм	SOT323.SC70	B-F-C





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
K19	DTA115GE	ROHM	Dpnp	V _{CB0} =50B; I _C =100 мА; P _D =150 мВт; h ₂₁ >82; f _T >250 МГц; R ₂ =100 кОм	S0T416,SC75A	B·E·C
K19	DTA115GKA	ROHM	Donio	V _{CRO} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >82; f _T >250 MFu; R ₂ =100 kOm	SOT346,SC59	B·E·C
K19	DTA115GUA	ROHM	Dpnp	V _{CR0} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >82; f _T >250 MFu; R ₂ =100 kOm	SOT323,SC70	B·E·C
K1E	BC847A	DIODS	non	V _{CP0} =50B; I _C =100 mA; P ₀ =300 mBT; h ₂₁ =110220; f ₇ =300 MFц	SOT23.SOD23	B-E-C
K1E	BC848A	DIODS	non	V _{CR0} =30B; I _C =100 mA; P _D =300 mBT; h ₂₁ =110220; f _T =300 MFц	SOT23,SOD23	B-E-C
KIF	BC847B	DIODS	non	V _{CB0} =50 B; I _C =100 mA; P ₀ =300 mBT; h ₂₁ =200450; f ₇ =300 MFц	SOT23,SOD23	B-E-C
K1F	BC848B	DIODS	non	V _{CRO} =30 B; I _C =100 mA; P _D =300 mBr; h ₂₁ =200450; f _T =300 MFц	SOT23,SOD23	B·E·C
KIG	MMSTA05	DIODS	non	V _{CR0} =60 B; I _C =500 mA; h ₂₁ > 100; f _T > 100 MFu	SOT323,SC70	0.000
KIG	MMSTA06	DIODS	non	V _{CBD} =80B; I _C =500 mA; h ₂₁ >100; f _T >100 MFu	SOT323,SC70	
	MMSTA05	DIODS	non	V _{CBD} =60 B; I _C =500 mA; h ₂₁ > 100; f _T > 100 MFu	SOT323,SC70	
K1J	BC848A	DIODS	non	V _{CR0} =30B; I _C =100 mA; P _D =300 mBt; h _{Pl} =110220; f _T =300 MFu	SOT23,SOD23	
KIK	BC848B	DIODS	non	V _{CBO} =30B; I _C =100 мA; P _D =300 мBτ; h ₂₁ =200450; f _T =300 MΓι ₄	SOT23.SOD23	
K1L	BC848C	DIODS	non	V _{CBO} =30B; I _C =100 мА; P _D =300 мВт; h ₂₁ =420800; f _T =300 МГц	SOT23.SOD23	10000000000
K1M	BC847C	DIODS	non	V _{CBO} =50B; I _C =100 mA; P _D =300 mB1; h ₂₁ =420800; f _T =300 MFu	SOT23,SOD23	200000000000000000000000000000000000000
	BC848C	DIODS	non	V _{CR0} =30B; I _C =100 MA; P _D =300 MB; H ₂₁ =420800; I _T =300 MFu	SOT23,SOD23	0.00.00
_		_	-			
KIN	MMBT3904	VISH	npn	V _{CB0} = 60 B; I _C = 100 mA; P _D = 200 mBr; h ₂₁ = 100300; f _T > 300 MFu	SOT23,SOD23	
	KSA3265	SAMS	npn	V _{CB0} =30 B; I _C =800 mA; P _D =200 mBτ; h ₂₁ =100200; f _T >120 MΓц	SOT23,SOD23	
K1p	BCW71	PHIL	npn	V _{CB0} =50 B; I _C =100 мА; P _D =250 мВт; h ₂₁ =110220; f _T >100 МГц	SOT23,SOD23	and the second second
	MMBT2222A	VISH	npn	V_{CB0} = 50 B; I_C = 800 mA; P_D = 200 mBt; h_{21} = 100300; f_T > 200 MFu	S0T23,S0D23	T-0070-70
	BC846A	DIODS	npn	V_{CB0} =80B; I_C =100 mA; P_D =150 mBt; h_{21} =110220; f_T =300 M Γ_{LL}	SOT23,SOD23	122.52 10
K1Q	BC847A	DIODS	npn	V_{CB0} =50 B; I_C =100 mA; P_D =300 mBt; h_{21} =110220; f_T =300 M Γ_{II}	SOT23,SOD23	
K1Q	BC848A	DIODS	npn	V_{CB0} =30 B; I_C =100 mA; P_D =300 mBT; h_{21} =110220; f_T =300 MF ι_I	SOT23,SOD23	
KIR	BC846B	DIODS	npn	V _{CB0} =80 B; I _C =100 mA; P _D =300 mBT; h ₂₁ =200450; f _T =300 MFu	SOT23,SOD23	B·E·C
KIR	BC847B	DIODS	non	V_{CB0} =50 B; I_C =100 mA; P_D =300 mBT; h_{21} =200450; f_T =300 MFц	SOT23,SOD23	B·E·C
K1R	BC848B	DIODS	npn	V_{CB0} =30 B; I_C =100 mA; P_D =300 mBT; h_{21} =200450; f_T =300 MF $_{LL}$	SOT23,SOD23	B·E·C
K1t	BCW71	PHIL	npn	V_{CB0} =50 B; I_C =100 mA; P_D =250 mBr; h_{21} =110220; f_T >100 MFu	SOT23,SOD23	B·E·C
K1Y	KSA3265	SAMS	npn	V_{CB0} =30B; I_C =800 mA; P_D =200 mBt; h_{21} =160320; f_T >120 MFu	SOT23,SOD23	B·E·C
K2	BCW72	ALLEG	npn	V _{CB0} *50 B; I _{CB0} <100 нA; h ₂₁ *200450; V _{CE(sat)} <0.25 B	SOT23,SOD23	B·E·C
K2	BCW72	CDIL	npn	V _{CB0} =50B; I _C =100 мА; P _D =250 мВт; h ₂₁ =200450; f _T >100 МГц	SOT23,SOD23	B·E·C
K2	BCW72	ZETEX	npn	V_{CB0} =50 B; I_C =100 mA; P_D =330 mBt; h_{21} =200450; f_T >300 MFu	SOT23,SOD23	B·E·C
K2	HSMP3832	HP	pin×2	I _F <1A;V _{BR} >200 B;R _S <1.50м;С ₀ <0.3пФ	SOT23,SOD23	A1 · K2 · K1,A2
K2	MMBZ5252BT	DIODS	dz	V _Z (I _{ZT} =5.2 mA)=22.825.2 B; I _B <0.1 m kA	SOT523	A•n.c.•K
K24	DTC114GKA	ROHM	Dnpn	V _{CR0} =50B; I _C =100 mA; P _D =200 mBr; h ₂₁ >30; f _T >250 MFu; R ₂ =10 kOm	SOT346,SC59	B·E·C
K24	DTC114GUA	ROHM	Dnpn	V _{CB0} =50B; I _C =100 mA; P _D =200 mBr; h _{P1} >30; f _T >250 MFu; R _P =10 kOm	SOT323,SC70	B·E·C
K25	DTA124GKA	ROHM	Dono	V _{CRD} =50B; I _C =100 mA; P _D =200 mBt; h ₂₁ >56; f ₁ >250 MFu; R ₂ =22 kOm	SOT346,SC59	B·E·C
K25	DTA124GUA	ROHM	Dpnp	V _{CB0} = 50 B; I _C = 100 мА; P _D = 200 мВт; h ₂₁ > 56; f _T > 250 МГц; R ₂ = 22 кОм	SOT323,SC70	B·E·C
K25	DTC124GKA	ROHM	Dnon	V _{CP0} =50 B; I _C =100 mA; P ₀ =200 mBT; h ₂₁ >56; f _T >250 MFu; R ₂ =22 KOm	SOT346.SC59	B·E·C
K25	DTC124GUA	ROHM	Dnon	V _{CR0} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >56; f _T >250 MFu; R ₂ =22 kOm	SOT323.SC70	B·E·C
K26	DTC144GE	ROHM	Dnon	V _{CBD} =50B; I _C =100 мA; P _D =200 мВт; h ₂₁ >68; f _T >250 МГц; R ₂ =47 кОм	SOT416.SC75A	200000000
K26	DTC144GKA	ROHM	Dnon	V _{CB0} =50B; I _C =100 mA; P _D =200 mBτ; h ₂₁ >68; f _T >250 MΓu; R ₂ =47 κOm	SOT346,SC59	
K26	DTC144GUA	ROHM	Dnpn	V _{CR0} =50B; I _C =100 mA; P _D =200 mBT; h ₂₁ >68; f _T >250 MFu; R ₂ =47 кОм	SOT323,SC70	
K29	DTC115GE	ROHM	Dnon	V _{CRD} =50B; I _D =100 mA; P _D =150 mBT; h ₂₁ >82; f _T >250 MFu; R ₂ =100 kOm	S0T416,SC75A	
K29	DTC115GKA	ROHM	Dnon	V _{CRD} =50B; I _C =100 MA; P _D =200 MBT; h ₂₁ >82; f _T > 250 MFu; R ₂ =100 kOM	SOT346,SC59	
K29	DTC115GUA	ROHM	Dnpn	V _{CB0} =50B; I _C =100 MA; P _D =200 MBT; h ₂₁ >82; f _T >250 MFu; R ₂ =100 KOM	SOT323,SC70	
K2D	MMSTA13	DIODS	dnpn	V _{CR0} =30B; I _C =300 MA; h ₂₁ >5000; f _T >125 MΓμ	SOT323,SC70	150000000000000000000000000000000000000
K2E	MMSTA63	DIODS	dpnp	V _{CB0} =30B; I _C =500 мА; h ₂₁ >5000; f ₇ >125 МГц	SOT323,SC70	10.762 20
K2F	MMBT2907A	VISH	ono	V _{CB0} =30B, I _C =300 MA; N ₂₁ > 3000, I _T > 120 MI L V _{CB0} =40B; I _C =500 MA; P _D =310 MB;; h ₂₁ =100300; f _T > 200 MFL	SOT23.SOD23	12.150.30
	MMSTA55	DIODS	onp	V _{CB0} =40B; I _C =500 MA; I _{P0} =310 MBT; I _{P1} =100300; I _T >200 MT Ц V _{CB0} =60B; I _C =500 MA; I _{P1} >100; I _T >50 MT Ц	SOT323,SOD23	
K2G		DIODS				
1.100.00	MMSTA56	10.000.00	pnp	V _{CB0} =80 B; I _C =500 mA; h ₂₁ >100; f ₁ >50 MΓц	SOT323,SC70	
	MMSTA55	DIODS	pnp	V _{CB0} =60 B; I _C =500 mA; h ₂₁ >100; f ₇ >50 MFu	SOT323,SC70	100000000000000000000000000000000000000
K2p	BCW72	PHIL	npn	V _{CBO} =50B; I _C =100 mA; P _D =250 mBr; h ₂₁ =200450; f ₇ >100 MF _U	SOT23,SOD23	1001000100
K2t	BCW72	PHIL	non	V_{CB0} =50B; I_C =100 mA; P_D =250 mBT; h_{21} =200450; f_T >100 MF $_{44}$	SOT23,SOD23	R.F.C

SOT490 TESM VMT3 1 3 SOT523 SOT323 SOT23-3 1 3 SOT523 SOT323 SOT3

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
K2T	MMBT4403	VISH	pnp	V _{GB0} =40 B; I _C =800 MA; P _D =200 MBT; h ₂₁ =100300; f _T >200 MFu	SOT23,SOD23	B·E·C
K2X	MMBT4401	VISH	npn	V_{CB0} =50 B; I_C =800 MA; P_D =200 MBT; h_{21} =100300; f_T >200 MF $_{II}$	SOT23,SOD23	B·E·C
K3	BCW81	CDIL	non	V _{GB0} =50 B; I _G =100 мА; P _D =250 мВт; h ₂₁ =420800; f _T >100 МГц	SOT23,SOD23	B·E·C
K3	HSMP3833	HP	pin×2	I _E <1A;V _{BB} >200 B;R _S <1.5 O _M ; C _D <0.3 πΦ	SOT23.SOD23	K1-K2-A1,A2
K31	BCW81R	PHIL	non	V_{CB0} =50 B; I_C =100 mA; P_D =350 mBT; h_{21} =420800; f_T =300 MF $_{II}$	SOT23,SOD23	E-B-C
КЗА	BC856A	DIODS	ono	V_{CB0} =80 B; I_C =100 MA; P_D =300 MBT; h_{21} =125250; f_T >100 MF $_{\rm II}$	SOT23,SOD23	B·E·C
КЗА	BC857A	DIODS	onp	V _{ово} =50 B; I _C =100 мА; P _D =300 мВт; h ₂₁ =110220; f _T >100 МГц	SOT23,SOD23	B·E·C
КЗА	BC858A	DIODS	ono	V _{CR0} =30 B; I _C =100 мА; P _D =300 мВт; h ₂₁ =125250; f _T >100 МГц	SOT23,SOD23	
КЗА	KDV804S	KEC	bd×2	V _B =15B,I _B =50нA;C2B=42.7пФ;C _{BB} =25пФ;R _S <0.3 Ом	SOT23,SOD23	
КЗВ	BC856B	DIODS	ono	V _{CB0} =80 B; I _C =100 MA, P _D =300 MB; h ₂₁ =220475; f _Y >100 MFu	SOT23,SOD23	
КЗВ	BC857B	DIODS	onp	V _{GB0} =50 B; I _C =100 mA; P _D =300 mBr; h ₂₁ =200450; f _T >100 MF _U	SOT23,SOD23	
КЗВ	BC858B	DIODS	ono	V _{GBO} =30 B; I _C =100 мА; P _D =300 мВт; h ₂₁ =220475; f _T >100 МГц	SOT23,SOD23	17503270000
K3B	DTA1D3RE	ROHM	Dono	V _{CB0} =50 B; I _{C(max)} =100 мA; P _D =150 мBт; h ₂₁ >20; f _T >250 МГц	SOT416.SC75A	100000130
K3B	DTA1D3RKA	ROHM	Dono	V _{CR0} =50 B; I _C =30 MA; P _D =200 MB; h ₂₁ >20; f _T >250 MFu; R ₁ /R ₂ =2.7/1 kOM	SOT346.SC59	Marco 277 (193)
K3B	DTA1D3RUA	ROHM	Dono	V _{GB0} =50 B; I _{Climaxl} =100 mA; P _D =200 mBr; h ₂₁ > 20; f _T > 250 MFu	SOT323.SC70	
K3B	KDV804S	KEC	bd×2	V _B =15B;I _B =50HA;C2B=43.7πΦ;C _{BB} =25πΦ;B _S <0.3 OM	SOT23,SOD23	
K3C	KDV804S	KEC	bd×2	V _R =15B;I _R =50HA;C2B=44.7nΦ;C _{8B} =25nΦ;B _S <0.3 OM	SOT23,SOD23	
K3D	KDV804S	KEC	bd×2	V _R =15B;I _R =50HA;C2B=45.7nΦ;C _{RR} =25nΦ;R _S <0.3 OM	SOT23,SOD23	
K3D	MMSTA13	DIODS	dnon	V _{GB1} =30 B; I _G =300 мA; h ₂₁ >5000; f ₇ >125 МГц	SOT323,SC70	
K3D	MMSTA14	DIODS	dnon	V _{CR0} =30 B; I _C =300 мA; h ₂₁ >30000; f ₇ >125 МГц	SOT323,SC70	1107 12 130
K3E	KDV804S	KEC	bd×2	V _B =15B;I _B =50нA;C2B=46.7nФ;C _{BB} =25nФ;R _S <0.3 Ом	SOT23,SOD23	
K3E	MMSTA63	DIODS	dpno	V _{GB} =30 B; I _G =500 MA; I _{ZE} >5000; f _T >125 MΓ _{LL}	SOT323,SC70	
K3E	MMSTA64	DIODS	dpno	V _{CR0} =30 B; I _C =500 MA; I _{C2} >30000; I _T >125 MFu,	SOT323,SC70	
K3G	BC857C	DIODS		V_{CR0} =50 B; I_C =500 MA; P_D =150 MB;; P_{24} =420800; f_T >300 MF $_{4}$	SOT23,SOD23	
K3G	BC858C	DIODS	pnp	V _{CBB} =30 B; I _C =100 MA; P _D =130 MBT; N ₂₁ =420800; I _T >300 MTq V _{CBB} =30 B; I _C =100 MA; P _D =300 MBT; N ₂₁ =420800; I _T >100 MTq	SOT23,SOD23	
K3J	BC858A		pnp	330 - 3 - 5 - 7 - 1		
K3K	BC858B	DIODS	pnp	V _{CBO} =30 B; I _C =100 mA; P _O =300 mBr; h ₂₁ =125250; f _T >100 MFu	SOT23,SOD23 SOT23,SOD23	100000000000000000000000000000000000000
K3L	BC858C	DIODS	pnp	V _{CBO} =30 B; I _C =100 mA; P _O =300 mBr; h ₂₁ =220475; f _T >100 MFц		
			pnp	V _{CB0} =30 B; I _C =100 мA; P _D =300 мBτ; h ₂₁ =420800; f _T >100 MΓ _U	SOT23,SOD23	
K3N	MMBT3906	VISH	pnp	V _{CB0} =40 B; I _C =100 mA; P _D =200 mBt; h ₂₁ =100300; f _T >250 MFu	SOT23,SOD23	200000000000000000000000000000000000000
КЗр	BCW81	PHIL	npn	V _{CB0} =50 B; I _C =100 мА; P _D =350 мВт; h ₂₁ =420800; f _T =300 МГц	SOT23,SOD23	1000000000
K3t	BCW81	PHIL	npn	V _{CB0} =50 B; I _C =100 мA; P _D =350 мВт; h ₂₁ =420800; f ₁ =300 МГц	SOT23,SOD23	10000000
K3V	BC857A	DIODS	pnp	V _{CB0} =50 B; I _C =100 мA; P _D =300 мВт; h ₂₁ =110220; f _T >100 МГц	SOT23,SOD23	E. C.
K3V	BC858A	DIODS	pnp	V_{CB0} =30 B; I_C =100 mA; P_D =300 mBt; h_{21} =125250; f_T >100 MFu	SOT23,SOD23	
K3W	BC857B	DIODS	pnp	V_{CB0} =50 B; I_C = 100 mA; P_D =300 mBT; h_{21} =200450; f_T >100 MFu	SOT23,SOD23	
K3W	BC858B	DIODS	pnp	V _{CBO} =30 B; I _C =100 мА; P _D =300 мВт; h ₂₁ =220475; f _T > 100 МГц	SOT23,SOD23	-
K4	BCW71R	PHIL	npn	V _{CBO} =45 B; I _C =100 мА; P _D =350 мВт; h ₂₁ =110220; f _T > 100 МГц	SOT23,SOD23	200000000000000000000000000000000000000
K4	BCW71R	ZETEX	npn	V _{CB0} =50 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =110220; f _T >300 МГц	SOT23,SOD23	
K4	HSMP3834	HP	pin×2	I _F <1A;V _{BR} >200 В; R _S <1.5 Ом; С _О <0.3 пФ	SOT23,SOD23	S. S
K4	MMBZ5254BT	DIODS	dz	V ₂ (I _{ZT} =5.0 mA)=25.6528.35B; I _B <0.1 mrA	SOT523	A·n.c.·K
K43	BAS40	DIODS	shd	V_R <40 B; I_F <200 mA; V_F (I_F =40 mA)<1.0 B; I_R <0.2 mKA; C_D <5.0 n Φ ; I_{RR} <5 HC		
K44	BAS40-04	DIODS	shd×2	$V_R < 40 \text{ B}; I_F < 200 \text{ mA}; V_F (I_F = 40 \text{ mA}) < 1 \text{ B}; I_R < 1.0 \text{ mKA}; C_D < 5 \text{ n}\Phi; t_{PR} < 5 \text{ hc}$	SOT23,SOD23	
K45	BAS40-05	DIODS	shd×2	V_R <40 B; I_F <200 mA; V_F (I_F =40 mA)<1.0 B; I_R <0.2 mKA; C_D <5.0 n Φ ; I_{RR} <5 HC	SOT23,SOD23	
K46	BAS40-06	DIODS	shd×2	V_R < 40 B; I_F < 200 mA; V_R < I_F = 40 mA) < 1.0 B; I_R < 0.2 m kA; C_D < 5.0 n Φ ; I_{RR} < 5 HC	SOT23,SOD23	
K4B	DTC1D3RE	ROHM	Dnpn	V_{CB0} =50 B; $I_{C(max)}$ =100 mA; P_{D} =150 mBT; h_{21} > 20; f_{T} > 250 MFu,	SOT416,SC75A	1,000-000-000
K4B	DTC1D3RKA	ROHM	Dnpn	V_{CB0} =50 B; I_C =30 MA; P_D =200 MBT; h_{21} >20; f_T >250 MFU; R_1/R_2 =2.7/1 KOM	SOT416,SC75A	B·E·C
K4B	DTC1D3RUA	ROHM	Dnpn	V_{CB0} =50 B; $I_{C(max)}$ =100 mA; P_{D} =200 mBT; h_{21} >20; f_{T} >250 MFu,	SOT323,SC70	B-E-C
K5	BCW72R	PHIL	npn	V_{CB0} =45 B; I_C = 100 mA; P_D =350 mBt; h_{21} =200450; f_T > 100 MFц	SOT23,SOD23	
K5	BCW72R	ZETEX	npn	V_{CB0} =50 B; I_C =100 mA; P_D =330 mBT; h_{21} =200450; f_T >300 MF $_{11}$	SOT23,SOD23	B.E.C
K5	MMBZ5255BT	DIODS	dz	V _Z (I _{ZT} =4.5 mA)=26.629.4 B; I _R <0.1 mkA	SOT523	A·n.c.·K
	BAV170	DIODS	dl×2	V _B < 85 B; I _E < 215 mA; V _E (I _E = 150 mA) < 1.25 B; I _B < 0.005 mkA; C _D < 2.0 mΦ;		A1 • A2 • K1.K2





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
K52	BAV199	DIODS	dl×2	$V_R \le 85B$; $I_F \le 160$ mA; $V_R (I_F = 150$ mA) ≤ 1.25 B; $I_R \le 0.005$ mKA; $C_D = 2.0$ n Φ ; $I_{BB} \le 3000$ HC	SOT23,SOD23	A1 • K2 • K1,A2
K6	BCV71R	ZETEX	non	V _{CBD} =80B; I _C =100 мА; P _D =330 мВт; h ₂₁ =110220; f _T >300 МГц	SOT23,SOD23	B·E·C
K6	BCV71R	PHIL	npn	V _{CBD} =80B; I _C =100 мА; P _D =330 мВт; h ₂₁ =110220; f _T >300 МГц	SOT23,SOD23	C-B-E
K7	BCV71	CDIL	npn	V _{CBD} =80B; I _C =100 мА; P _D =330 мВт; h ₂₁ =110220; f _T >300 МГц	SOT23,SOD23	B·E·C
K7	BCV71	ZETEX	non	V _{CBD} =80B; I _C =100 мА; P _D =330 мВт; h ₂₁ =110220; f _T >300 МГц	SOT23,SOD23	B·E·C
K72	2N7002	DIODS	nFET	V _{DS} =60B;I _D =115мA;P _D =300мВт;V _{GSTH} =12.5B;C _{ISS} <50пФ	SOT23, SOD23	G-S-D
K73	BAS70	DIODS	shd	V _B <70B; I _E <70 mA; V _E (I _E =15 mA)<1.0B; I _B <0.1 mkA; C _D <2.0 mΦ; t _{BB} <5 hc	SOT23,SOD23	A·n.c.·K
K74	BAS70-04	DIODS	shd×2	V _B <70B; I _E <70 мA; V _E (I _E : 15 мA)<1.0B; I _B <0.1 мкA; C _D <2.0 пФ; t _{BB} <5нс	SOT23.SOD23	
K75	BAS70-05	DIODS	shd×2	V _B <70B; I _E <70 мA; V _E (I _E =15 мA)<1.0B; I _B <0.1 мкA; C _D <2.0 пФ; t _{BB} <5нс	SOT23 SOD23	A1-A2-K1.K2
K76	BAS70-06	DIODS	shd×2	$V_B < 70B; I_E < 70 \text{ mA}; V_E (I_E = 15 \text{ mA}) < 1.0B; I_B < 0.1 \text{ mkA}; C_D < 2.0 \text{ n}\Phi; I_{BB} < 5 \text{ hc}$	SOT23.SOD23	K1-K2-A1.A2
K7A	2N7002-01	DIODS	nFET	V _{DS} =60B;I _D =115мA;P _D =300мВт;V _{GSTH} =12B;C _{ISS} <50пФ	SOT23.SOD23	
K7C	BAS70	DIODS	shd	$V_B \le 70B$; $I_E \le 70$ mA; $V_E (I_E = 15$ mA) $\le 1.0B$; $I_B \le 0.1$ mkA; $C_D \le 2.0$ n Φ ; $t_{BB} \le 5$ HC	SOT23,SOD23	200000000000000000000000000000000000000
K7D	BAS70-04	DIODS	shd×2	V _B <70B; I _E <70 мA; V _E (I _E =15 мA)<1.0B; I _B <0.1 мкA; C _D <2.0 пФ; t _{BB} <5 нс	SOT23,SOD23	
K7E	BAS70-05	DIODS	shd×2	V _B <70B; I _c <70 mA; V _c (I _c =15 mA)<1.0B; I _B <0.1 mkA; C _D <2.0 nΦ; I _{cB} <5 hc	SOT23,SOD23	
K7E	BAS70-06	DIODS	shd×2	V _B <70B; I _E <70 mA; V _E (I _E =15 mA)<1.0B; I _B <0.1 mkA; C _D <2.0 nΦ; t _{BB} <5 hc	SOT23.SOD23	10000
K70	BCV71	PHIL	non	V _{CBD} =80B; I _C =100 мA; P _D =250 мBτ; h ₂₁ =110220; f _T >100 MΓц	SOT23,SOD23	
K7t	BCV71	PHIL	non	V _{CB0} =80 B; I _C =100 mA; P _D =250 mBr; h ₂₁ =110220; f _T >100 mFu	SOT23,SOD23	
K8	BCV72	CDIL	non	V _{CBO} *80 B; I _C *100 mA; I _C *230 mBr; I _D *2100450; I _T >300 MFu	SOT23,SOD23	
K8	BCV72	ZETEX	non	V _{CR0} =80B; I _C =100 MA; P _D =330 MBT; h ₂₁ =200450; f _T >300 MFu	SOT23,SOD23	250000000000000000000000000000000000000
K8o	BCV72	PHIL	non	V _{CB0} =80B; I _C =100 MA; P _D =350 MB; H ₂₁ =200450; f _T >350 MH t ₄	SOT23,SOD23	Land Company Company
K8t	BCV72	PHIL	non	V _{CB0} =80B; I _C =100 MA; P _D =250 MB; H ₂₁ =200450; f _T >100 MF _U	SOT23,SOD23	100000000000000000000000000000000000000
K9	1SS348	TOSH	shd	V _E >80 B; V _C (I _E =100 mA) < 0.7 B; I _B (V _E =80 B) < 5 mcA; C _T < 100 mΦ	SOT346.SC59	10 00 00
K9	BCV72R	ZETEX	non	1 1 11 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	SOT23,SOD23	
K9	BCV72R BCV72R	PHIL		V _{CB0} =80 B; I _C =100 mA; P _D =330 mBr; h ₂₁ =200450; f ₇ >300 MFu		
		PHIL	npn	V _{CB0} =80 B; I _C =100 mA; P _D =330 mBτ; h ₂₁ =200450; f _T >300 MΓιμ	SOT23,SOD23	
K91	BCF81R		npn	V _{CB0} =45B; I _C =100 mA; P _D =350 mBr; h ₂₁ =420800; f _T >100 MFų	SOT23,SOD23	
K9p	BCF81	PHIL	npn	V _{CB0} =50 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =420800; f _T >100 MFu	SOT23,SOD23	
KA	RN1441A	TOSH	Dnpn	V _{CB0} =50 B; I _C =300 мА; P _D =200 мВт; h ₂₁ =200700; f _T =30 МГц; R ₁ =5.6 кОм	SOT346,SC59	120000 000
KA2	MMBD4148	VISH	di	$V_R < 75B$; $I_F < 300 \text{ mA}$; $V_F (I_{F^2} 10 \text{ mA}) < 1.0B$; $I_R < 5.0 \text{ mkA}$; $C_0 < 4 \text{ n}\Phi$; $t_{PR} < 6 \text{ HC}$	SOT23,SOD23	
KA3	MMBD4448	VISH	fid	$V_R < 75B; I_F < 500 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 1.0B; I_R < 5.0 \text{ m/A}; C_D < 4 \text{ n}\Phi; t_{RR} < 4 \text{ Hc}$	SOT23,SOD23	
KA6	BAS16	VISH	fid	V_{R} <75B; I_{F} <500mA; V_{F} (I_{F} =150mA)<1.25B; I_{R} <1.0mkA; C_{D} <4.0n Φ ; I_{RR} <4 HC	SOT23,SOD23	
KA8	BAS19	DIODS	fd	V_R <100 В; I_F <250 мА; V_F (I_F =100 мА)<1.0 В; I_R <0.1 мкА; C_0 <5.0 пФ; I_{RR} <50 нс	SOT23,SOD23	A•n.c.•K
KA8	BAS19W	DIODS	fd	$V_R < 100 B_i I_F < 400 \text{mA}; V_F (I_F = 100 \text{mA}) < 1.0 B_i I_R < 0.1 \text{mkA}; C_0 < 5 \text{n/D}; I_{BR} < 50 \text{Hz}$	SOT323,SC70	A•n.c.•K
KB	MMBT8099LT1	ON	npn	V_{CB0} =80 B; I_C =500 mA; P_D =225 mBT; h_{21} =100300; f_T >150 M Γ_{II}	SOT23,SOD23	B·E·C
KB	RN1441B	TOSH	Dnpn	V_{CB0} = 50 B; I_C = 300 mA; P_D = 200 mBt; h_{21} = 3501200; f_T = 30 MFu; R_1 = 5.6 kOm	SOT346,SC59	B·E·C
KC	BFQ29P	SIEM	npn	V _{CB0} =20 B; I _C =30 мA; P _D =280 мВт; h ₂₁ =50250; f ₁ =5000 МГц	SOT23,SOD23	B·E·C
KD1	AZ23C2V7	DIODS	dz×2	Vz=2.52.9 B; Rz(Iz=5 mA) <83 Om	SOT23,SOD23	K1-K2-A1,A2
KD2	AZ23C3V0	DIODS	dz×2	Vz=2.83.2 B; Rz(Iz=5 mA) < 95 Om	SOT23,SOD23	K1-K2-A1,A2
KD3	AZ23C3V3	DIODS	dz×2	Vz=3.13.5 B; Rz(Iz=5 mA) < 95 Om	SOT23,SOD23	K1-K2-A1,A2
KD4	AZ23C3V6	DIODS	dz×2	Vz=3.43.8 B; Rz(Iz=5 mA) < 95 Om	SOT23,SOD23	K1-K2-A1,A2
KD5	AZ23C3V9	DIODS	dz×2	Vz=3.74.1 B; Rz(Iz=5 mA) <950m	SOT23,SOD23	K1-K2-A1,A2
KD6	AZ23C4V3	DIODS	dz×2	Vz=4.04.6 B; Rz(Iz=5 mA) <95 Om	SOT23,SOD23	K1 · K2 · A1 ,A2
KD7	AZ23C4V7	DIODS	dz×2	Vz=4.45.0 B; Rz(Iz=5 mA) < 78 0m	SOT23,SOD23	K1-K2-A1,A2
KD8	AZ23C5V1	DIODS	dz×2	Vz=4.85.4 B; Rz(Iz=5 mA) <60 Om	SOT23,SOD23	K1 · K2 · A1,A2
KD9	AZ23C5V6	DIODS	dz×2	Vz=5.26.0 B; Rz(Iz=5 mA) < 40 Om	SOT23,SOD23	K1-K2-A1,A2
KD9	AZ23C5V6W	DIODS	dz×2	V _z =5.325.88 B;R _z (I _z =5 mA)< 40 Om	SOT323,SC70	K1-K2-A1,A2
KDA	AZ23C6V2	DIODS	dz×2	V _Z =5.86.6 B; R _Z (I _Z =5 mA) < 10 Om	SOT23,SOD23	K1-K2-A1,A2
KDB	AZ23C6V8	DIODS	dz×2	V ₂ =6.47.2 B; R ₂ (I ₂ =5 mA) < 8 Om	SOT23,SOD23	K1-K2-A1.A2
KDB	AZ23C6V8W	DIODS	dz×2	V ₇ =6.477.14B;R ₇ (I ₇ =5mA)<8 Om	SOT323,SC70	
KDC	AZ23C7V5	DIODS	dz×2	V _z =7.07.9 B; R _z (I _z =5 mA) < 7.0 m	SOT23,SOD23	

Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
KDD	AZ23C8V2	DIODS	dz×2	Vz=7.78.7 B;Rz(Iz=5 mA) < 7 Om	SOT23,SOD23	K1·K2·A1,A2
KDE	AZ23C9V1	DIODS	dz×2	V2=8.59.6B;R2(I2=5 MA) < 10 OM	SOT23,SOD23	K1·K2·A1,A2
KDF	AZ23C10	DIODS	dz×2	V ₂ =9.410.6B;R ₂ (I ₂ =5mA)<15Om	SOT23,SOD23	K1-K2-A1,A2
KDF	AZ23C10W	DIODS	dz×2	V ₂ =9.410.6B;R ₂ (I ₂ =5mA)<15Om	SOT323,SC70	K1-K2-A1,A2
KDG	AZ23C11	DIODS	dz×2	Vz=10.411.6B;Rz(Iz=5mA)<20 Om	SOT23,SOD23	K1-K2-A1,A2
KDH	AZ23C12	DIODS	dz×2	V ₂ =11.412.7B;R ₂ (I ₂ =5mA)<20 Om	SOT23,SOD23	K1-K2-A1,A2
KDI	AZ23C13	DIODS	dz×2	Vz=12.414.1 B;Rz(Iz=5mA) < 25 Om	SOT23,SOD23	K1-K2-A1,A2
KDJ	AZ23C15	DIODS	dz×2	Vz=13.815.6B;Rz(Iz=5mA)<30 Om	SOT23,SOD23	K1-K2-A1,A2
KDK	AZ23C16	DIODS	dz×2	Vz=15.317.1B;Rz(Iz=5mA)<40 Om	SOT23,SOD23	K1-K2-A1,A2
KDL	AZ23C18	DIODS	dz×2	V2=16.819.1B;R2(I2=5MA)<50 OM	SOT23,SOD23	K1-K2-A1,A2
KDL	AZ23C18W	DIODS	dz×2	V ₂ =16.819.1 B;R ₂ (I ₂ =5 mA) < 50 Om	SOT323,SC70	K1-K2-A1,A2
KDM	AZ23C20	DIODS	dz×2	Vz=18.821.2B;Rz(Iz=5mA)<50.0m	SOT23,SOD23	K1-K2-A1,A2
KDN	AZ23C22	DIODS	dz×2	V ₂ =20.823.3B;R ₂ (I ₂ =5mA)<550m	SOT23,SOD23	K1-K2-A1,A2
KDO	AZ23C24	DIODS	dz×2	V2=22.825.6B;R2(I2=5MA)<80 OM	SOT23,SOD23	K1-K2-A1,A2
KDP	AZ23C27	DIODS	dz×2	Vz=25.128.9B;Rz(Iz=5mA)<80.0m	SOT23,SOD23	K1-K2-A1,A2
KDQ	AZ23C30	DIODS	dz×2	V ₇ =2832 B; R ₇ (I ₇ =5 mA) < 80 Om	SOT23,SOD23	K1-K2-A1,A2
KDR	AZ23C33	DIODS	dz×2	V2=3135 B; R2(I2=5 MA) < 80 OM	SOT23,SOD23	K1-K2-A1,A2
KDS	AZ23C36	DIODS	dz×2	V2=3438 B; R2(J2=5 MA) < 90 OM	SOT23,SOD23	K1-K2-A1,A2
KDT	AZ23C39	DIODS	dz×2	V ₂ =3741 B; R ₂ (I ₂ =5 mA) < 90 Om	SOT23.SOD23	The second second
KE	2SK1062	TOSH	nMOS	V _{DS} =60B;I _D =200 мA;P _D =200 мBT;R _{DS(on)} =0.6 Oм	SOT346,SC59	G-S-D
KF	2SJ168	TOSH		V _{DS} =60B;I _D =200 мA;P _D =200 мBт;R _{DSion} =1.3 0м	SOT346.SC59	325.55
KG	BRC123ECM	REN	Dnpn	V _{CC} =50 B; I _{OLIT} =100 мА; P _D =150 мВт; h ₂₁ >20; 2.2 к/2.2 к	SOT323.SC70	
KG	BRC123EMP	REN	Dnpn	V _{GG} =50 B; I _{DUT} =100 mA; P _D =150 mBT; h ₂₁ >20; 2.2 к/2.2 к	SOT23,SOD23	
KH	2SK1826	TOSH	_	V _{DS} =50 B; I _D =50 mA; P _D =200 mBT; R _{DStorn} =20 Om	SOT346.SC59	-
КН	2SK1827	TOSH	nFET	V _{DS} >50 B; I _D =50 mA; R _{DS(ort)} <50 Om; g _E >20 mCm; P _D =100 mBr	SOT323,SC70	G·S·D
KI	2SK1828	TOSH	nMOS	V _{DS} =20B; I _D =50 mA; P _D =100 mBT; R _{DSIom} =20 Om	SOT346,SC59	
KI	2SK1829	TOSH	nMOS	V _{DS} >20 B; I _D =50 mA; R _{DS(on)} < 40 Om; g _F >20 mCm; P _D =100 mBt	SOT323,SC70	
кі	2SK1830	TOSH	nFET	V _{DS} =20B;I _D =50mA;P _D =200mBT;R _{DS(on)} =20 Om	SOT416,SC75A	
KID	2SC4050D	REN	non	V _{DB0} =120 B; I _C =100 mA; P _D =150 mB; h ₂₁ =250500	SOT23.SOD23	
KIE	2SC4050E	REN	ngn	V _{CB0} =120 B; I _C =100 mA; P _D =150 mBT; h ₂₁ =400800	SOT23,SOD23	B-E-C
KJ	2SK2036	TOSH	nMOS	V _{DS} =20B;I _D =100 MA;P _D =200 MBT;R _{DSioni} =3.5 OM	SOT346,SC59	G-S-D
KJ	2SK2037	TOSH		V _{DS} >20 B; I _D =100 mA; R _{DS(on)} <6 Om; g _F >35 mCm; P _D =100 mBt	SOT323,SC70	100.07.1
KJA	BAV70W	DIODS	di×2	V _B <75 B; I _E <300 mA; V _E (I _E =50 mA)<1.0 B; C _B <2 nΦ; t _{BB} <6 hc	SOT323,SC70	
KJC	BAW56W	DIODS	di×2	V _B < 75 B; I _E < 300 mA; V _E (I _E = 150 mA) < 1.25 B; I _B < 2 mKA; t _{BB} < 4 HC		K1-K2-A1.A2
KJD	BAW56	VISH	di×2	V_R < 70 B, I_e < 300 mA, V_e (I_e = 150 mA) < 1.25 B, I_R < 5.0 mxA, C_D < 4.0 n Φ ; I_{BR} < 6 HC	SOT23,SOD23	K1 · K2 · A1, A2
K.JE	BAV99	VISH	di×2	V _R <70 B, I _E <300 мA, V _E (I _E =150 мA)<1.25 B, I _R <5.0 мкA, C _D <4.0 пФ; I _{BR} <6 нС	SOT23,SOD23	A1 • K2 • K1,A2
KJE	BAV99	DIODS	di×2	V _B < 75 B; I _E < 300 mA; V _E (I _E = 150 mA) < 1.25 B; I _B < 2 mkA; t _{BB} < 4 Hc	SOT23,SOD23	A1-K2-K1,A2
KJF	BAL99	VISH	di	$V_R < 70 \text{ B}; I_F < 250 \text{ mA}; V_F (I_F = 50 \text{ mA}) < 1.0 \text{ B}; I_R < 2.5 \text{ m/sA}; C_D < 1.5 \text{ n}\Phi; I_{RR} < 6 \text{ Hc}$	SOT23,SOD23	n.c. · K·A
KJG	BAV99W	DIODS	di×2	V _B < 75 B; I _E < 300 mA; V _E (I _E = 150 mA) < 1.25 B; I _B < 2 mrA; t _{BB} < 4 hc	SOT323,SC70	A1 · K2 · K1, A2
KJG	BAV99W	DIOT	di×2	V _B < 70 B; I _E < 200 mA; V _E (I _E = 150 mA) < 1.25 B; I _B < 2 mrA; t _{BB} < 4 hc	SOT323,SC70	A1-K1,A2-K2
KJJ	BAV70	VISH	di×2	V_R < 70 B, I_F < 300 mA; V_F (I_F = 150 mA) < 1.25 B; I_R < 5.0 mkA; C_0 < 4.0 n Φ ; I_{BR} < 6 mc	SOT23,SOD23	A1-A2-K1,K2
KK	2SK2823	TOSH	nMOS	V _{DS} =20B;I _D =100 mA;P _D =200 mBT;R _{DSioni} =7 Om	SOT346,SC59	G·S·D
KK	2SK2824	TOSH	nMOS	V _{DS} >20 B; I _D =100 мA; R _{DS(on)} <28 Ом; g _E >35 мСм; P _D =100 мВт	SOT323,SC70	G·S·D
KK	2SK2825	TOSH	nFET	V _{DS} =20B;I _D =100 mA;P _D =200 mBT;R _{DS(on)} =10 0m	SOT416,SC75A	
KL1	BAT54	DIOT	shd	V _B < 30 B; I _E < 300 mA; V _E (I _E =30 mA) < 500 mB; C _D < 10 mΦ; t _{BB} < 5 Hc	SOT23,SOD23	
KL1	BAT54	DIODS	shd	V _B <30 B; I _F < 200 mA; V _F (I _F = 30 mA) < 500 mB; C _D < 10 mΦ; t _{BB} < 5 Hc	SOT23,SOD23	100000000000000000000000000000000000000
KL1	BAT54	VISH	shd	V _B <30 B; I _E <200 mA; V _E (I _E =100 mA)<1.0 B; I _B <2 mrA; C _D <10 mΦ; t _{BB} <5 hc	SOT23,SOD23	200700000000000000000000000000000000000
KL2	BAS54A	VISH		V _B =30 B; I _F =200 mA; P _D =200 mBr; t _{RR} <5 hc	SOT23,SOD23	
KL2	BAT54A	DIOT	_	V _B <30 B; I _F <300 мA; V _F (I _F =30 мA)<500 мB; C _D <10 пФ; t _{BB} <5 нс	SOT23,SOD23	





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
KL2	BAT54A	DIODS	shd×2	$V_R \le 30 \text{ B}; I_F \le 200 \text{ mA}; V_F (I_F = 30 \text{ mA}) \le 500 \text{ mB}; C_D \le 10 \text{ n}\Phi; t_{BR} \le 5 \text{ hc}$	SOT23,SOD23	K1 · K2 · A1,A2
KL2	BAT54A	VISH	shd×2	$V_B < 30B$; $I_E < 200 \text{ mA}$; $V_E (I_E = 100 \text{ mA}) < 1.0B$; $I_B < 2.0 \text{ m/A}$; $C_D < 10 \text{ m/D}$; $t_{BB} < 5 \text{ m/D}$	SOT23,SOD23	K1-K2-A1,A2
KL3	BAS54C	VISH	shd×2	V _B =30 B; I _E =200 mA; P _D =200 mBr; t _{BB} <5 Hc	SOT23,SOD23	A1-A2-K1,K2
KL3	BAT54B	VISH	shd×2	$V_B < 30B$; $I_E < 200 \text{ MA}$; $V_E (I_E = 100 \text{ MA}) < 1.0B$; $I_B < 2.0 \text{ M/A}$; $C_D < 10 \text{ m/D}$; $t_{BB} < 5 \text{ Hz}$	SOT23,SOD23	A1-A2-K1,K2
KL3	BAT54C	DIOT	shd×2	$V_R < 30 \text{ B; } I_F < 300 \text{ mA; } V_E (I_F = 30 \text{ mA}) < 500 \text{ mB; } C_D < 10 \text{ n}\Phi; t_{RR} < 5 \text{ Hc}$	SOT23,SOD23	A1-A2-K1,K2
KL3	BAT54C	DIODS	shd×2	$V_R < 30 \text{ B; } I_F < 200 \text{ mA; } V_E (I_F = 30 \text{ mA}) < 500 \text{ mB; } C_D < 10 \text{ n}\Phi; t_{BR} < 5 \text{ Hc}$	SOT23,SOD23	A1-A2-K1,K2
KL4	BAS54S	VISH	shd×2	V _R =30 B; I _F =200 mA; P _D =200 mBr; t _{RR} <5 Hc	SOT23,SOD23	A1-K2-K1,A2
KL4	BAT54S	DIOT	shd×2	$V_R < 30 \text{ B; } I_F < 300 \text{ mA; } V_R (I_F = 30 \text{ mA}) < 500 \text{ mB; } C_D < 10 \text{ n}\Phi; t_{RR} < 5 \text{ Hc}$	SOT23,SOD23	A1-K2-K1,A2
KL4	BAT54S	DIODS	shd×2	$V_R < 30 \text{ B; } I_F < 200 \text{ mA; } V_R (I_F = 30 \text{ mA}) < 500 \text{ mB; } C_D < 10 \text{ m} \Phi; I_{RR} < 5 \text{ Hc}$	SOT23,SOD23	A1-K2-K1,A2
KL4	BAT54S	VISH	shd×2	$V_R < 30 \text{ B}; I_F < 200 \text{ mA}; V_R (I_F = 100 \text{ mA}) < 1.0 \text{ B}; I_R < 2.0 \text{ m/A}; C_D < 10 \text{ m/D}; I_{RR} < 5 \text{ Hz}$	SOT23,SOD23	A1 · K2 · K1, A2
KM	2SK2009	TOSH	nMOS	V _{DS} =30B;I _D =200 mA; P _D =200 mBT; R _{DS(on)} =1.2 Om	SOT346,SC59	G•S•D
KN	2SJ305	TOSH	pMOS	V _{DS} =30B;I _D =200mA;P _D =200mBT;R _{DS(on)} =2.4 Om	SOT346,SC59	G·S·D
KP	2SK2033	TOSH	nMOS	V _{DS} =20B;I _D =100mA;P _D =200mBT;R _{DS(on)} =80m	SOT346,SC59	G·S·D
KP	2SK2034	TOSH	nMOS	V _{DS} >20B; I _D =100 mA; R _{DS(on)} < 12 Om; g _F >25 mCm; P _D =100 mBT	SOT323,SC70	G·S·D
KP	2SK2035	TOSH	nFET	V _{DS} =20B;I _D =100mA;P _D =200mBT;R _{DS(on)} =80m	SOT416,SC75A	G·S·D
KQ	2SJ343	TOSH	pMOS	V _{DS} =50 B; I _D =50 мА; P _D =200 мВт; R _{DS(on)} =20 Ом	SOT346,SC59	G·S·D
KQ	2SJ344	TOSH	pMOS	$V_{DS}>50 B; I_D=50 mA; R_{DS(on)}<50 Om; g_F>15 mCm; P_D=100 mBT$	SOT323,SC70	G·S·D
KS	2SJ345	TOSH	pMOS	V _{DS} =20B;I _D =50 mA;P _D =200 mBT;R _{DS(on)} =20 Om	SOT346,SC59	G·S·D
KS	2SJ346	TOSH	pMOS	V _{DS} >20B; I _D =50 mA; R _{DS(on)} <40 Om; g _F >15 mCm; P _D =100 mBt	SOT323,SC70	G·S·D
KS	2SJ347	TOSH	pFET	V _{DS} =20B; I _D =50 mA; P _D =200 mBT; R _{DS(on)} =20 Om	SOT416,SC75A	G·S·D
KT2	BAS19	DIODS	fd	V_R < 100 B; I_F < 250 mA; V_F (I_F = 100 mA) < 1.0 B; I_R < 0.1 m;A; C_0 < 5.0 n Φ ; I_{BR} < 50 HC	S0T23,S0D23	A+n.c.+K
KT2	BAS19W	DIODS	fd	V _R < 100 B; I _E < 400 мA; V _E (I _E = 100 мA) < 1.0 B; I _R < 0.1 мкА; C _D < 5 пФ; I _{ER} < 50 нс	S0T323,SC70	A+n.c.+K
KT2	BAS20	DIODS	fd	$V_R < 150 B; I_F < 250 mA; V_F (I_F = 100 mA) < 1.0 B; I_R < 0.1 m kA; C_0 < 5.0 n\Phi; t_{RR} < 50 Hc$	SOT23,SOD23	A•n.c.•K
KT2	BAS20W	DIODS	fd	$V_R < 150 B_i I_F < 400 \text{mA}_i V_F (I_F = 100 \text{mA}_i) < 1.0 B_i I_R < 0.1 \text{mxA}_i C_0 < 5.0 \text{n} \Phi_i + 1.0 B_i I_R < 0.1 \text{mxA}_i C_0 < 5.0 \text{n} \Phi_i$	SOT323,SC70	A•n.c.•K
KT3	BAS19	DIODS	fd	V_R < 100 B; I_F < 250 мА; V_F (I_F = 100 мА) < 1.0 B; I_R < 0.1 мкА; C_0 < 5.0 п Φ ; I_{RR} < 50 нс	S0T23,S0D23	A•n.c.•K
KT3	BAS19W	DIODS	fd	$V_R < 100 B; I_F < 400 \text{mA}; V_R I_{F^2} = 100 \text{mA}) < 1.0 B; I_R < 0.1 \text{mkA}; C_D < 5 \text{n}\Phi; t_{BR} < 50 \text{Hz}$	S0T323,SC70	A•n.c.•K
KT3	BAS20	DIODS	fd	V _R <150 B; I _F <250 мА; V _P (I _F =100 мА)<1.0 B; I _R <0.1 мкА; C _D <5.0 пФ; I _{BR} <50 нс	SOT23,SOD23	A•n.c.•K
KT3	BAS20W	DIODS	fd	$V_R <$ 150 B; $I_F <$ 400 mA; $V_F (I_F = 100$ mA) $<$ 1.0 B; $I_R <$ 0.1 mKA; $C_0 <$ 5.0 n Φ ; $I_{RR} <$ 50 Hz	S0T323,SC70	A•n.c.•K
KT3	BAS21	DIODS	di	V_R <200 В; I_F <250 мА; V_F (I_F =100 мА)<1.0 В; I_R <0.1 мкА; C_0 <5.0 п Φ ; I_{RR} <50 нс	SOT23,SOD23	A•n.c.•K
KT3	BAS21	DIODS	di	V_R < 200 B; I_F < 400 мA; V_P (I_F = 100 мA) < 1.0 B; I_R < 0.1 мкA; C_0 < 5.0 п Φ ; I_{RR} < 50 нс	S0T323,SC70	A•n.c.•K
KV	1SV264	SANYO	pin×2	V _B >50 B; I _E <50 mA; V _E (I _E =50 mA) < 0.95 B; I _B < 0.1 mkA	SOT323,SC70	A1 · K2 · K1,A2
KV	1SV267	SANYO	pin×2	V _B >50 B; I _E <50 mA; V _E (I _E =50 mA)=0.91 B; I _B <0.1 mkA	SOT23,SOD23	A1 · K2 · K1,A2
KV1	DZ23C2V7	VISH	dz×2	Vz=2.52.9 B; Zzt(Iz=5 mA)=830m	SOT23,SOD23	A1-A2-K1,K2
KV1	DZ23C2V7	DIODS	dz×2	Vz=2.52.9 B; Zz1(Iz=5 mA)=83 Om	SOT23,SOD23	A1-A2-K1,K2
KV2	DZ23C3V0	VISH	dz×2	Vz=2.83.2 B; Zzt{Iz=5 mA}=950m	SOT23,SOD23	A1+A2+K1,K2
KV2	DZ23C3V0	DIODS	dz×2	V _Z =2.83.2 B; Z _{ZT} (I _Z =5 mA)=950m	SOT23,SOD23	A1-A2-K1,K2
KV3	DZ23C3V3	VISH	dz×2	V _Z =3.13.5 B; Z _{ZT} (I _Z =5 mA)=950m	SOT23,SOD23	A1 • A2 • K1, K2
KV3	DZ23C3V3	DIODS	dz×2	Vz=3.13.5 B; Zz1(Iz=5 mA)=950m	SOT23,SOD23	A1+A2+K1,K2
KV4	DZ23C3V6	VISH	dz×2	Vz=3.43.8 B; Zzt{Iz=5 mA}=950m	SOT23,SOD23	A1-A2-K1,K2
KV4	DZ23C3V6	DIODS	dz×2	Vz=3.43.8 B; Zzt(Iz=5 mA)=950m	SOT23,SOD23	A1-A2-K1,K2
<v5< td=""><td>DZ23C3V9</td><td>VISH</td><td>dz×2</td><td>Vz=3.74.1 B; Zzt(Iz=5 mA)=950m</td><td>SOT23,SOD23</td><td>A1-A2-K1,K2</td></v5<>	DZ23C3V9	VISH	dz×2	Vz=3.74.1 B; Zzt(Iz=5 mA)=950m	SOT23,SOD23	A1-A2-K1,K2
KV5	DZ23C3V9	DIODS	dz×2	Vz=3.74.1 B; Zzy(Iz=5 mA)=95 Om	SOT23,SOD23	A1 • A2 • K1, K2
KV6	DZ23C4V3	VISH	dz×2	Vz=4.04.6 B; Zzr(lz=5 mA)=95 Om	SOT23,SOD23	A1-A2-K1,K2
KV6	DZ23C4V3	DIODS	dz×2	Vz=4.04.6 B; Zzz(Iz=5 mA)=950m	SOT23.SOD23	A1-A2-K1.K2

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Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
KV7	DZ23C4V7	VISH	dz×2	Vz=4.45.0 B; Zz;(Iz=5 mA)=78 Om	SOT23,SOD23	A1-A2-K1,K2
KV7	DZ23C4V7	DIODS	dz×2	Vz=4.04.6B;Zzt(Iz=5mA)=950m	SOT23,SOD23	A1+A2+K1,K2
KV8	DZ23C5V1	VISH	dz×2	V _Z =4.85.4B;Z _{ZT} (I _Z =5 mA)=60 Om	SOT23,SOD23	A1+A2+K1,K2
KV8	DZ23C5V1	DIODS	dz×2	Vz=4.85.4B;Zzt(Iz=5mA)=60 Om	SOT23,SOD23	A1+A2+K1,K2
KV9	DZ23C5V6	VISH	dz×2	Vz=5.26.0 B; Zz; (Iz=5 mA)=40 Om	SOT23,SOD23	A1-A2-K1,K2
KV9	DZ23C5V6	DIODS	dz×2	Vz=5.26.0 B; Zz; (Iz=5 mA)=40 Om	SOT23,SOD23	A1-A2-K1,K2
KVA	DZ23C6V2	VISH	dz×2	V _Z =5.86.6 B; Z _{ZT} (I _Z =5 MA)= 10 Om	SOT23,SOD23	A1-A2-K1,K2
KVA	DZ23C6V2	DIODS	dz×2	Vz=5.86.6B;Zzt(Iz=5mA)=10 Om	SOT23,SOD23	A1-A2-K1,K2
KVB	DZ23C6V8	VISH	dz×2	Vz=6.47.2B;Zzt(Iz=5mA)=80m	SOT23,SOD23	A1-A2-K1,K2
KVB	DZ23C6V8	DIODS	dz×2	Vz=6.47.2B;Zz;(Iz=5mA)=80m	SOT23,SOD23	A1-A2-K1,K2
KVC	DZ23C7V5	VISH	dz×2	Vz=7.07.9B;Zzt(Iz=5mA)=7Om	SOT23,SOD23	A1+A2+K1,K2
KVC	DZ23C7V5	DIODS	dz×2	Vz=7.07.9B;Zz;(Iz=5mA)=7Om	SOT23,SOD23	A1-A2-K1,K2
KVD	DZ23C8V2	VISH	dz×2	Vz=7.78.7B;Zz;(Iz=5mA)=70m	SOT23,SOD23	A1-A2-K1,K2
KVD	DZ23C8V2	DIODS	dz×2	Vz=7.78.7B;Zzt(Iz=5mA)=70m	SOT23,SOD23	A1-A2-K1,K2
KVE	DZ23C9V1	VISH	dz×2	V ₂ =8.59.6B;Z _{ZT} (I ₂ =5mA)=10 Om	SOT23,SOD23	A1-A2-K1,K2
KVE	DZ23C9V1	DIODS	dz×2	Vz=8.59.6 B; Zzt(Iz=5 mA)=10 Om	SOT23,SOD23	
KVF	DZ23C10	VISH	dz×2	V ₂ =9.410.B; Z ₂₇ {I ₂ =5mA}=150m	SOT23,SOD23	A1-A2-K1,K2
KVF	DZ23C10	DIODS	dz×2	V ₂ =9.410.B ₁ Z ₂₇ {I ₂ =5mA}=150m	SOT23,SOD23	A1-A2-K1,K2
KVG	DZ23C11	VISH	dz×2	Vz=10.411.B; Zzt(Iz=5 mA)=20 Om	SOT23,SOD23	A1-A2-K1.K2
KVG	DZ23C11	DIODS	dz×2	V ₂ =10.411.B; Z _{Z1} (I _Z =5 mA)=20 Om	SOT23,SOD23	
KVH	DZ23C12	VISH	dz×2	V ₂ =11.412.B; Z ₂₁ (I ₂ =5 mA)=20 Om	SOT23,SOD23	
KVH	DZ23C12	DIODS	dz×2	V ₂ =11.412.B; Z _{Z1} (I _Z =5 mA)=20 Om	SOT23,SOD23	
KVI	DZ23C13	VISH	dz×2	V _z =12.414.B; Z _{z1} (I _z =5 mA)=25 Om	SOT23,SOD23	
KVI	DZ23C13	DIODS	dz×2	V ₂ =12.414.B; Z _{Z1} (I ₂ =5 mA)=25 Om	SOT23,SOD23	
KVJ	DZ23C15	VISH	dz×2	V ₂ =13.815.B; Z _{Z1} (I ₂ =5 MA)=30 OM	SOT23,SOD23	
KVJ	DZ23C15	DIODS	dz×2	V ₂ =13.815.B; Z ₂₇ (I ₂ =5 mA)=30 Om	SOT23,SOD23	
KVK	DZ23C16	VISH	dz×2	V _z =15.317.B; Z _{zz} (I _z =5 mA)=40 0m	SOT23,SOD23	
KVK	DZ23C16	DIODS	dz×2	V ₂ =15.317.B; Z ₂₁ (I ₂ =5 mA) =40 Om	SOT23,SOD23	
KVL	DZ23C18	VISH	dz×2	V ₂ =16.819.B; Z ₂₁ (I ₂ =5 mA)=50 Om	SOT23,SOD23	
KVL	DZ23C18	DIODS	dz×2	V ₂ =16.819.B; Z ₂₇ (I ₂ =5 mA)=50 Om	SOT23,SOD23	
KVM	DZ23C20	VISH	dz×2	V ₂ =18.821.B; Z ₂₁ (I ₂ =5 mA)=50 Om	SOT23,SOD23	
KVM	DZ23C20	DIODS	dz×2	V ₂ =18.821.B; Z _{Z1} (I ₂ =5 mA)=50 Om	SOT23,SOD23	
KVN	DZ23C22	VISH	dz×2	V _z =20.823.B; Z _{zt} (I _z =5 mA)=55 Om	SOT23,SOD23	
KVN	DZ23C22	DIODS	dz×2	V _z =20.823.B; Z _{z1} (I _z =5 MA) =55 OM	SOT23,SOD23	
KVO	DZ23C24	VISH	dz×2	V _z =22.825.B; Z _{Z1} (I _z =5 MA)=80 OM	SOT23,SOD23	V
KVO	DZ23C24	DIODS	dz×2	V ₂ =22.825.B; Z ₇₁ (I ₂ =5 mA)=80 Om	SOT23,SOD23	
KVP	DZ23C27	VISH	dz×2	V _z =25.128.B; Z _{z1} (I _z =2 MA)=80 OM	SOT23,SOD23	
KVP	DZ23C27	DIODS	dz×2	V ₂ =25.128.B; Z _{Z1} (I _Z =2 mA)=80 Om	SOT23,SOD23	
KVQ	DZ23C30	VISH	dz×2	V ₂ =2832 B; Z ₂₇ (I ₂ =2 mA)=80 Om	SOT23,SOD23	
KVQ	DZ23C30	DIODS	dz×2	V ₂ =2832 B; Z ₂₇ (I ₂ =2 mA)=80 Om	SOT23,SOD23	-
KVR	DZ23C33	VISH	dz×2	V _z =3135 B; Z _{z7} (I _z =2 mA)=80 Om	SOT23,SOD23	
KVR	DZ23C33	DIODS	dz×2	V _z =3135 B; Z _{zzf} {I _z =2 mA}=80 Om	SOT23,SOD23	-
KVS	DZ23C36	VISH	dz×2	V ₂ =3438 B; Z ₂₇ {I ₂ =2 mA}=90 Om	SOT23,SOD23	
KVS	DZ23C36	DIODS	dz×2	V ₂ =3438 B; Z ₂₇ {I ₂ =2 MA}=90 OM	SOT23,SOD23	
KVT	DZ23C39	VISH	dz×2	Vz=3741 B; Zz;(Iz=2 MA)=90 OM	SOT23,SOD23	
KVT	DZ23C39	DIODS	dz×2	V _z =3741 B; Z _{z1} (I _z =2 MA)=90 OM	SOT23,SOD23	
KVU	DZ23C43	VISH	dz×2	V ₂ =4046 B; Z ₂₇ {I ₂ =2 MA}=100 Om	SOT23,SOD23	
KVU	DZ23C43	DIODS	dz×2	V ₂ =4046 B; Z ₂₇ (I ₂ =2 MA)=100 Om	SOT23,SOD23	
KW	DZ23C47	VISH	dz×2	V _Z =4450 B; Z _{ZT} (I _Z =2 MA)=100 Om	SOT23,SOD23	
KW	DZ23C47	DIODS	dz×2	V ₇ =4450 B; Z ₇₇ {I ₇ =2 mA}=100 Om	SOT23,SOD23	
KVW	DZ23C51	VISH	dz×2	V _Z =4854 B; Z _Z (I _Z =2 mA)=100 0m	SOT23,SOD23	
KVW	DZ23C51	DIODS	dz×2	V ₇ =4854 B; Z ₇₇ (I ₇ =2 MA)=100 Om	SOT23,SOD23	
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Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
KY1	BZX84C11	VISH	dz	V _Z (I _{ZT} =5 MA)=10.411.6B;Z _{ZT} (I _{ZT} =5 MA)<20 OM	SOT23,SOD23	A·n.c.·K
KY2	BZX84C12	VISH	dz	V _Z (I _{ZT} =5 mA)=11.412.7 B;Z _{Z1} (I _{ZT} =5 mA)<250m	SOT23,SOD23	A+n.c.+K
KY3	BZX84C13	VISH	dz	V _Z (I _{ZT} =5 mA)=12.414.1B;Z _{ZT} (I _{ZT} =5 mA)<30 Om	SOT23,SOD23	A·n.c.·K
KY4	BZX84C15	VISH	dz	V _Z (I _{ZT} =5 mA)=13.815.6B;Z _{ZT} (I _{ZT} =5 mA)<30 Om	SOT23,SOD23	A+n.c.+K
KY5	BZX84C16	VISH	dz	V _Z (I _{ZT} =5mA)=15.317.1B;Z _{ZT} (I _{ZT} =5mA)<40.0m	SOT23,SOD23	A+n.c.+K
KY6	BZX84C18	VISH	dz	V _Z (I _{ZT} =5 mA)=16.819.1B; Z _{ZT} (I _{ZT} =5 mA)<45 Om	SOT23,SOD23	A·n.c.·K
KY7	BZX84C20	VISH	dz	V ₂ (I ₂₇ =5 MA)=18.821.2B; Z ₂₇ (I ₂₇ =5 MA)<55 OM	SOT23,SOD23	A·n.c.·K
KY8	BZX84C22	VISH	dz	V ₇ (I ₇₇ =5 mA)=20.823.3B; Z ₇₇ (I ₇₇ =5 mA)<55 Om	SOT23,SOD23	A·n.c.·K
KY9	BZX84C24	VISH	dz	V ₂ (I _{2T} =5 mA)=22.825.6B; Z _{2T} (I _{2T} =5 mA)<70 Om	SOT23.SOD23	
KYA	BZX84C27	VISH	dz	V ₂ (I _{2T} =2 MA)=25.128.9 B; Z _{2T} (I _{2T} =2 MA) < 80 OM	SOT23.SOD23	
KYB	BZX84C30	VISH	dz	V _Z (I _{ZT} = 2 MA) = 28.032.0 B; Z _{ZT} (I _{ZT} = 2 MA) < 80 OM	SOT23,SOD23	
KYC	BZX84C33	VISH	dz	V _Z (I _{ZT} = 2 mA) = 31.035.0B; Z _{ZT} (I _{ZT} = 2 mA) < 80 Om	SOT23,SOD23	1901 1100 1100 1100
KYD	BZX84C36	VISH	dz	V _Z (I _{ZT} =2 MA)=33.038.0B; Z _{ZT} (I _{ZT} =2 MA) < 90 OM	SOT23,SOD23	
KYE	BZX84C39	VISH	dz	V ₂ (I _{2T} = 2 mA) = 36.041.0B; Z ₂₇ (I _{2T} = 2 mA) < 1300m	SOT23.SOD23	200
KYE	BZX84C43	VISH	dz	V ₇ (I _{7T} = 2 mA) = 40.046.0 B; Z ₂₇ (I _{2T} = 2 mA) < 150 Om	SOT23,SOD23	100000000000000000000000000000000000000
KYG	BZX84C47	VISH	dz	V _Z (I _{ZT} 2 MA) = 44.050.0B; Z _Z T(I _{ZT} 2 MA) < 1700M	SOT23,SOD23	
KYH	BZX84C51	VISH	dz	V _Z (_{ZT} = 2mA) = 48.054.0B; Z _{ZT} (_{ZT} = 2mA) < 1800m	SOT23,SOD23	
KZ1	BZX84C4V7	VISH	dz	$V_{Z(Z_{1}^{-2} 5MA)}$ = 4.45.0 B; $Z_{Z(1}(Z_{1}^{-2} 5MA)$ < 80 OM	SOT23,SOD23	100000000000000000000000000000000000000
KZ2		VISH	-		SOT23,SOD23	SEC. 10. 10. 10. 10. 10. 10. 10. 10. 10. 10
	BZX84C5V1	10.77	dz	V _Z (I _{ZT} =5 MA)=4.85.4B; Z _{ZT} (I _{ZT} =5 MA)<60 OM		10 10 10 10 10 10 10 10 10 10 10 10 10 1
KZ3	BZX84C5V6	VISH	dz	V _Z (I _{ZT} =5mA)=526.0 B;Z _{ZT} (I _{ZT} =5mA)<400m	SOT23,SOD23	1.00.00.00.00.00.00.00.00.00.00.00.00.00
KZ4	BZX84C6V2	VISH	dz	V _Z (I _{ZT} =5mA)=5.86.6B;Z _{Z1} (I _{ZT} =5mA)<100m	SOT23,SOD23	
KZ5	BZX84C6V8	VISH	dz	V _Z (I _{ZT} =5 MA)=647.2B;Z _{Z1} (I _{ZT} =5 MA)<15 OM	SOT23,SOD23	
KZ6	BZX84C7V5	VISH	dz	V _Z (I _{ZT} =5 mA)=7.07.9 B;Z _{ZT} (I _{ZT} =5 mA)<15 Om	SOT23,SOD23	
KZ7	BZX84C8V2	VISH	dz	V _Z (I _{ZT} =5 MA)=7.78.9 B;Z _{ZT} (I _{ZT} =5 MA)<15 Om	SOT23,SOD23	
KZ8	BZX84C9V1	VISH	dz	V _Z (I _{ZT} =5 mA)=8.59.6 B ; Z _{ZT} (I _{ZT} =5 mA)<15 Om	SOT23,SOD23	12.000
KZ9	BZX84C10	VISH	dz	V _Z (I _{ZT} =5 MA)=9.410.6 B; Z _{ZT} (I _{ZT} =5 MA) < 20 Om	SOT23,SOD23	
KZC	BZX84C2V7	VISH	dz	V _Z (I _{ZT} =5 MA)=2.512.89 B; Z _{ZT} (I _{ZT} =5 MA) < 100 OM	SOT23,SOD23	
KZD	BZX84C3V0	VISH	dz	$V_Z(I_{ZT}=5.0 \text{ mA})=2.83.2 \text{ B}; Z_{ZT}(I_{ZT}=5.0 \text{ mA}) \le 100 \text{ Om}$	SOT23,SOD23	
KZE	BZX84C3V3	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA})=3.13.5 \text{ B}; Z_{ZT}(I_{ZT}=5 \text{ mA}) < 95 \text{ Om}$	SOT23,SOD23	
KZF	BZX84C3V6	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA})=3.43.8 \text{ B}; Z_{ZT}(I_{ZT}=5 \text{ mA}) \le 95 \text{ Om}$	SOT23,SOD23	A+n.c.+K
KZG	BZX84C3V9	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA})=3.74.1 \text{ B}; Z_{ZT}(I_{ZT}=5 \text{ mA}) \le 90 \text{ Om}$	SOT23,SOD23	100 mm 100 mm
KZH	BZX84C4V3	VISH	dz	$V_Z(I_{ZT}=5 \text{ mA})=4.04.6 \text{ B}; Z_{ZT}(I_{ZT}=5 \text{ mA}) \le 90 \text{ Om}$	SOT23,SOD23	A·n.c.·K
LO	HSMP3860	HP	pin	I _F <1A;V _{BR} >50B;R _S (typ)=3.0 Ом;С _D (typ)=0.20 пФ	SOT23,SOD23	A·n.c.·K
LO	HSMP386B	HP	pin	I _F <1A;V _{BR} >50B;R _S (typ)=3.00м;СТ(typ)=0.20 пФ	SOT323,SC70	A+n.c.+K
L05	ZLLS500	ZETEX	shd	$V_R < 40 \text{ B}; I_F < 0.7 \text{ A}; V_F (I_F = 0.75 \text{ A}) < 0.63 \text{ B}; I_R < 10 \text{ m/sA}; C_D = 16 \text{ n}\Phi$	SOT23,SOD23	A·n.c.·K
LOp	BAT721S	PHIL	shd×2	$V_B < 40 \text{ B}; I_E < 200 \text{ mA}; V_E (I_E = 100 \text{ mA}) < 0.42 \text{ B}; I_B < 15 \text{ mrA}; C_D < 50 \text{ n}\Phi$	SOT23,SOD23	A1 · K2 · K1,A2
LOt	BAT721S	PHIL	shd×2	V _B <40 B; I _E <200 мА; V _E (I _E =100 мА)<0.42 B; I _B <15 мкА; С _D <50 пФ	SOT23,SOD23	A1 · K2 · K1,A2
LOW	BAT721S	PHIL	shd×2	$V_B < 40 \text{ B}; I_E < 200 \text{ mA}; V_E (I_E = 100 \text{ mA}) < 0.42 \text{ B}; I_B < 15 \text{ mrA}; C_D < 50 \text{ n}\Phi$	SOT23,SOD23	A1+K2+K1,A2
L1	BSS65	ZETEX	pnp	$V_{CB0}=12B; I_C=100 \text{ mA}; P_0=330 \text{ mBT}; h_{21}=40150; f_T>400 \text{ MFц}$	SOT23,SOD23	B·E·C
L10	ZLLS1000	ZETEX	shd	V _B <40B; I _E <1.16 A; I _B <20 мкА	SOT23,SOD23	A+n.c.+K
L14	DTB114GK	ROHM	Dono	V _{CR0} =50B; I _C =500 mA; P _D =200 mBt; h ₂₁ >56; f _T >200 MFu; R ₂ =10 kOm	SOT346,SC59	B-E-C
L14	DTD114GK	ROHM	Dnpn	V _{GB0} =50B; I _G =500 мА; P _B =200 мВт; h ₂₁ >56; f _T >200 МГц; R ₂ =10 кОм	SOT346,SC59	
L2	BSS69	ZETEX	pnp	V _{CB0} =40 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =50150; f _T >200 МГц	SOT23.SOD23	
L2	HSMP3862	HP	pin×2	$I_{E} \le 1A; V_{BB} \ge 50B; R_{S}(typ) = 3.0 \text{ OM}; C_{D}(typ) = 0.20 \text{ n}\Phi$	SOT23,SOD23	A1-K2-K1.A2
 L2	HSMP386C	HP	pin×2	I _F <1A;V _{RR} >50B;R _s (typ)=3.00м;СТ(typ)=0.20пФ	SOT323,SC70	100000000000000000000000000000000000000
L2	KTC4075	KEC	non	V _{CB0} =60 B; I _C =150 мА; P ₀ =100 мВт; h ₂₁ =70140; f _T >80 МГц	SOT323,SC70	
L20	BAS29	PHIL	di	V _B <90 B; I _F <250 mA; V _E (I _F =200 mA)<1.0 B; C _D <35 nΦ; t _{BB} <50	SOT23,SOD23	12 50 10
L20	CMPD1001	CSI	dih	I _F <250 mA; V _R =90 B; V _F (I _F =10 mA) < 0.75 B; I _R <100 nA; I _{RR} <50 nC; C _T <35 nΦ	SOT23,SOD23	
L20	KSK211	SAMS	nFET	V _{DS} =18B; P _D =200 MBT; I _{DSS} >1 MA; Q _F >9 MCM	SOT23,SOD23	
L21	BAS31	PHIL	di×2	V _R <90B; I _E <250 MA; V _E (I _E =200 MA)<1.0B; C _R <35 nΦ; t _{RR} <50 HC	SOT23,SOD23	700000000
	CMPD1001S	CSI	dih×2		SOT23,50D23	
L21						DE DI DERI

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
L22	CMPD1001A	CSI	dih×2	$I_F < 250 \text{ mA; } V_B = 90 \text{ B; } V_E (I_F = 10 \text{ mA}) < 0.75 \text{ B; } I_B < 100 \text{ mA; } t_{BB} < 50 \text{ hc; } C_T < 35 \text{ n}\Phi$	SOT23,SOD23	K2·K1·A2,A1
L24	DTD114GK	ROHM	Dnpn	V _{CR0} *50 B; I _C *500 мА; P _D *200 мВт; h ₂₁ >56; f _T > 200 МГц; R ₂ * 10 кОм	SOT23,SOD23	B·E·C
L24	DTD114GK	ROHM	Dnpn	V _{CP0} =50 B; I _C =500 mA; P _D =200 mBr; h ₂₁ >56; f _T >200 MFu; R ₂ =10 kOm	SOT346,SC59	B·E·C
L3	BSS70	ZETEX	ono	V _{сво} = 40 B; I _C = 100 мА; P _D = 330 мВт; h ₂₁ = 100300; f _T > 250 МГц	SOT23,SOD23	B-E-C
L3	HSMP3863	HP	pin×2	$I_E < 1A; V_{BB} > 50 B; R_s(typ) = 3.0 Om; C_n(typ) = 0.20 n\Phi$	SOT23,SOD23	K1-K2-A1,A2
L3	HSMP386E	HP	oin×2	I _E < 1A; V _{BB} >50 B; R _S (typ)=3.0 O _M ; CT(typ)=0.20 πΦ	SOT323.SC70	K1-K2-A1.A2
L3	KST1623L3	SAMS	non	V _{DB0} =50 B; I _D =100 мА; P _D =350 мВт; h ₂₁ =60120; I _T >200 МГц	SOT23,SOD23	B·E·C
L3	MMBC1623L3	MOT	non	V _{CR0} =50 B; I _C =100 mA; P _D =300 mBT; h ₂₁ =60120	SOT23,SOD23	
L31	BAV23S	PHIL	d×2	V _B <200 B; I _F <225 mA; V _F (I _F = 100 mA) < 1.0 B; C _B <5πΦ; t _{BB} <50 HC	SOT23,SOD23	
L4	BAT54	PANJIT	shd	V _B <30 B; I _E <300 mA; V _E (I _E =100 mA) < 1 B	SOT23,SOD23	
L4	BAT54	TSC	shd	V _B <30 B; I _F <300 мA; V _F (I _F =30 мA)<500 мB; C _D <10 пФ; t _{BB} <5 нс	SOT23,SOD23	
L4	BAT54	GS	shd	V _B <30 B; I _E <200 mA; V _E (I _E =30 mA) < 500 mB; C _D <10 nΦ; t _{BB} <5 hc	SOT23,SOD23	
L4	BAT54	DIOT	shd	V _B <30 B; I _F <300 мA; V _F (I _F =30 мA)<500 мB; C _D <10 пФ; t _{BB} <5 нс	SOT23,SOD23	100000000000000000000000000000000000000
L4	BAT54	VISH	shd	V _B <30 B; I _F <200 mA; V _E (I _F =100 mA) < 1.0 B; I _B <2 mxA; C _D <10 nΦ; t _{BB} <5 hc	SOT23,SOD23	
L4	BAT54W	PHIL	shd	V _B <30 B; I _E <200 mA; V _E (I _E =1 mA)<320 mB; C _B <10 nΦ; t _{BB} <5 hc	SOT323,30023	100000000000000000000000000000000000000
L4 L4	HSMP3864	HP	pin×2		SOT23,SOD23	
L4 L4	HSMP386F	HP	process.	I _F <1A;V _{BR} >50 B; R _S (typ)=3.0 O _M ; CT(typ)=0.20 πΦ		
		*.**	pin×2	I _F <1A;V _{BR} >50 B; R _S (typ)=3.0 O _M ; CT(typ)=0.20 nΦ	SOT323,SC70	
L4	KST1623L4	SAMS	npn	V _{CB0} =50 B; I _C =100 mA; P _D =350 mBt; h ₂₁ =90180; f _T >200 MFu	SOT23,SOD23	T005T4076
L4	KTC4075	KEC	npn	V _{CB0} =60 B;I _C = 150 мА; P _D =100 мВт; h ₂₁ =120240; f _T >80 МГц	SOT323,SC70	200 E 50
L4	MMBC1623L4	MOT	npn	V _{CB0} =50 B; I _C =100 mA; P _D =300 mBT; h ₂₁ =90180	SOT23,SOD23	12222 22
L42	BAT54A	PHIL	shd×2	V _R <30 В; I _F <200 мА; V _F (I _F =30 мА) < 500 мВ; С ₀ <10 пФ; t _{RR} <5 нс	SOT23,SOD23	
L42	BAT54A	MCC	shd×2	V _R <30 B; I _F <300 mA; V _F (I _F =30 mA)<500 mB; C _D <10 nΦ; t _{RR} <5 Hc	SOT23,SOD23	
L42	BAT54A			V _R <30 B; I _F <300 mA; V _F (I _F =100 mA)<1 B	SOT23,SOD23	
L42	BAT54A	TSC	shd×2	$V_R < 30 \text{ B; } I_F < 300 \text{ mA; } V_F (I_F = 30 \text{ mA}) < 500 \text{ mB; } C_D < 10 \text{ m\Phi; } t_{RR} < 5 \text{ Hc}$	SOT23,SOD23	Section Control of Control
L42	BAT54A	GS	shd×2	V _R <30 B; I _F <200 мA; V _F (I _F =30 мA)<500 мB; C _D <10 пФ; t _{RR} <5 нс	SOT23,SOD23	The second second
L42	BAT54A	DIOT	shd×2	$V_R < 30 \text{ B; } I_F < 300 \text{ MA; } V_F (I_F = 30 \text{ MA}) < 500 \text{ MB; } C_D < 10 \text{ m$$\Phi$; } t_{BR} < 5 \text{ Hc}$	SOT23,SOD23	K1 · K2 · A1, A2
L42	BAT54A	Nat	shd×2	$V_R \le 30 \text{ B}; I_F \le 200 \text{ mA}; V_F (I_F = 30 \text{ mA}) \le 500 \text{ mB}; C_D \le 10 \text{ m}\Phi; t_{RR} \le 5 \text{ Hz}$	SOT23,SOD23	K1 · K2 · A1, A2
L42	BAT54A	VISH	shd×2	$V_R < 30 \text{ B; } I_F < 200 \text{ mA; } V_F (I_F = 100 \text{ mA}) < 1.0 \text{ B; } I_R < 2.0 \text{ mkA; } C_D < 10 \text{ n}\Phi; I_{FR} < 5 \text{ hc}$	SOT23,SOD23	K1 · K2 · A1, A2
L42	BAT54A	ZETEX	shd×2	$V_R < 30 \text{ B}; I_F < 200 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 1.0 \text{ B}; I_R < 4.0 \text{ mkA}; C_0 < 10 \text{ n}\Phi; I_{PR} < 5 \text{ hc}$	SOT23,SOD23	K1-K2-A1,A2
L43	BAT54B	VISH	shd×2	$V_B \le 30 \text{ B}; I_E \le 200 \text{ mA}; V_E (I_E = 100 \text{ mA}) \le 1.0 \text{ B}; I_R \le 2.0 \text{ m/sA}; C_D \le 10 \text{ n}\Phi; I_{RR} \le 5 \text{ Hc}$	SOT23,SOD23	A1+A2+K1,K2
L43	BAT54C	PHIL	shd×2	$V_R \le 30 \text{ B; } I_F \le 200 \text{ mA; } V_F (I_F = 30 \text{ mA}) \le 500 \text{ mB; } C_D \le 10 \text{ m\Phi; } t_{RR} \le 5 \text{ Hc}$	SOT23,SOD23	A1-A2-K1,K2
L43	BAT54C	MCC	shd×2	V _B < 30 B; I _E < 300 мА; V _E (I _E = 30 мА) < 500 мВ; C _D < 10 пФ; t _{BB} < 5 нс	SOT23,SOD23	A1+A2+K1,K2
L43	BAT54C	PANJIT	shd×2	V _R < 30 B; I _F < 300 mA; V _F (I _F = 100 mA) < 1 B	SOT23,SOD23	A1-A2-K1,K2
L43	BAT54C	TSC	shd×2	$V_R < 30 \text{ B; } I_F < 300 \text{ mA; } V_F (I_F = 30 \text{ mA}) < 500 \text{ mB; } C_D < 10 \text{ n\Phi; } t_{RR} < 5 \text{ Hc}$	SOT23,SOD23	A1-A2-K1,K2
L43	BAT54C	GS	shd×2	V _B < 30 B; I _E < 200 мА; V _E (I _E = 30 мА) < 500 мВ; С _D < 10 пФ; t _{BB} < 5 нс	SOT23,SOD23	A1-A2-K1,K2
L43	BAT54C	DIOT	shd×2	$V_B \le 30 \text{ B; } I_E \le 300 \text{ mA; } V_E (I_E = 30 \text{ mA}) \le 500 \text{ mB; } C_D \le 10 \text{ n\Phi; } t_{DB} \le 5 \text{ Hc}$	SOT23,SOD23	A1+A2+K1,K2
L43	BAT54C	Nat	shd×2	V _B < 30 B; I _E < 200 мА; V _E (I _E =30 мА) < 500 мВ; С _D < 10 пФ; t _{BB} < 5 нс	SOT23,SOD23	A1-A2-K1,K2
L43	BAT54C	VISH	shd×2	V _R =30 B; I _E =200 mA; P _D =200 mBT; t _{RR} < 5 HC	SOT23,SOD23	A1-A2-K1.K2
L43	BAT54C	ZETEX	shd×2	$V_B < 30 \text{ B}; I_F < 200 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 1.0 \text{ B}; I_B < 4.0 \text{ mKA}; C_0 < 10 \text{ n}\Phi; t_{BB} < 5 \text{ hc}$	2/2/2010/10/2010	
L44	BAT54S	PHIL	shd×2	V _B < 30 B; I _E < 200 мA; V _E (I _E =30 мA) < 500 мB; C _D < 10 пФ; t _{BB} < 5 нс	SOT23,SOD23	
L44	BAT54S	MCC	shd×2	V _B <30 B; I _F <300 mA; V _F (I _F =30 mA) <500 mB; C _D <10 mΦ; t _{BB} <5 hc	SOT23,SOD23	
L44	BAT54S	PANJIT	shd×2	V _B < 30 B; I _F < 300 mA; V _F (I _F = 100 mA) < 1 B	SOT23,SOD23	
L44	BAT54S	TSC		V _B <30 B, I _F <300 мA; V _F (I _F =30 мA)<500 мB; C _B <10 пФ; t _{BB} <5 нс	SOT23,SOD23	-
L44	BAT54S	GS		V _B <30 B; I _c <200 MA; V _C (I _c =30 MA)<500 MB; C _D <10 mΦ; t _{DB} <5 hc	SOT23,SOD23	The second second
L44	BAT54S	DIOT	shd×2	V _R <30 B; I _F <300 MA; V _F (I _F =30 MA)<500 MB; C _R <10 mΦ; t _{RR} <5 hc	SOT23,SOD23	
L44	BAT54S	Nat		V _B <30 B; I _F <200 mA; V _F (I _F =30 mA)<500 mB; C _D <10 mΦ; t _{BB} <5 nc	SOT23,SOD23	
L44	BAT54S	VISH	shd×2	$V_R < 30 B; I_F < 200 MA; V_F (I_F = 100 MA) < 1.0 B; I_R < 2.0 MKA; C_R < 10 n \Phi; t_{RR} < 5 Hc$	SOT23,SOD23	The state of the s
L44 L44	BAT54S	ZETEX	shd×2	$V_B \le 0.0 \text{ K}, I_F \le 200 \text{ MA}, V_F I_F = 100 \text{ MA} \times 1.0 \text{ B}, I_B \le 2.0 \text{ MA}, C_0 \le 10 \text{ TO}, I_B B \le 5 \text{ Hz}$	SOT23,SOD23	
L44 L40	BAT54	PHIL	shd×2		-	
- P				V _R <30 B; I _F <200 мА; V _F (I _F =30 мА)<500 мВ; C _D <10 пФ; t _{RR} <5нс	SOT23,SOD23	
L4P	BAT54	MCC	shd	V _R <30 B; I _F <300 мА; V _F (I _F =30 мА)<500 мВ; C _D <10 пФ; t _{RR} <5нс	SOT23,SOD23	5
L4p	BAT54	Nat	shd	V _R <30 B; I _F <200 мA; V _F (I _F =30 мA)<500 мB; C _D <10 пФ; t _{RR} <5 нс	SOT23,SOD23	
L4t	BAT54	PHIL	shd	$V_R < 30 \text{ B; } I_F < 200 \text{ mA; } V_F (I_F = 30 \text{ mA}) < 500 \text{ mB; } C_D < 10 \text{ n\Phi; } t_{RR} < 5 \text{ Hc}$	SOT23,SOD23	A·n.c.·K





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
4W	BAT54	PHIL	shd	V _B <30B; I _F <200 mA; V _E (I _F =30 mA)<500 mB; C _D <10 nΦ; t _{BB} <5 hc	SOT23,SOD23	A·n.c.·K
.4Z	BAT54	ZETEX	shd	$V_B \le 30B$; $I_E \le 200 \text{ mA}$; $V_E (I_E = 100 \text{ mA}) \le 1.0B$; $I_B \le 4.0 \text{ m/A}$; $C_D \le 10 \text{ m/P}$; $t_{BR} \le 5 \text{ Hz}$	SOT23,SOD23	
.5	BSS65R	ZETEX	pnp	V _{CB0} = 12B; I _C = 100 мА; P _D = 330 мВт; h ₂₁ =40150; f _T >400 МГц	SOT23,SOD23	B·E·C
L5	KST1623L5	SAMS	non	V _{CP0} =50B; I _C =100 mA; P ₀ =350 mBτ; h ₂₁ =135270; f ₁ >200 MΓu	SOT23.SOD23	B-E-C
L5	MMBC1623L5	MOT	non	V _{CR0} =50B; I _C =100 mA; P _D =300 mBt; h ₂₁ =1350270	SOT23,SOD23	B-E-C
L52	BAS678	PHIL	fd	V _B <80B; I _E <250 mA; V _E (I _E =200 mA)<1.0B; C _D <2 nΦ; t _{bB} <6 hc	SOT23.SOD23	120000000000000000000000000000000000000
L5p	BAS55	PHIL	fd	V _B <60 B; I _E <250 mA; V _E (I _E =200 mA)<1.0 B; C _D <2.5 mD; t _{BB} <6 hc	SOT23,SOD23	100,000
L6	BAR17	INF	pin	V _B <100B; I _E <140 mA; V _E (I _E =100 mA)<1.0B; I _B <0.05 m×A; C _D <0.37 пФ	SOT23,SOD23	100000000000000000000000000000000000000
L6	BSS69R	ZETEX	onp	V _{CR0} =40 B; I _C =100 мА; P _П =330 мВт; h ₂₁ =50150; f _T >200 МГц	SOT23.SOD23	
L6	KST1623L6	SAMS	non	V _{CB0} =50 B; I _C =100 mA; P _D =350 mBτ; h ₂₁ =200400; f _T >200 MΓu	SOT23,SOD23	
L6	KTC4075	KEC	non	V _{CR0} =60B; I _C =150 MA; P _D =100 MBT; h ₂₁ =200400; f _T >80 MFµ	SOT323,SC70	
L6	MMBC1623L6	MOT	non	V _{CBO} =50B; I _C =100 mA; P _D =300 mBT; h ₂₁ =200400	SOT23.SOD23	100017651191
L7	BAR141	INF	pin×2	V _B <100 B; I _E <140 mA; V _E (I _E =100 mA)<1.05 B; I _B <0.1 mkA; C _D <0.2 πΦ	SOT23,SOD23	-
L7	BAT17	GS	shd	V _R <4B; I _F <30 mA; V _F (I _F =1 mA)<450 mB; C _D <1 πΦ	SOT23,SOD23	
L7	BAT17DS	GS	shd×2	V _R <4B; I _F <30 MA; V _F (I _F =1 MA)<450 MB; C _R <1 πΦ	SOT23,SOD23	
L7		_	_			
	BSS70R	ZETEX	pnp	V _{CBO} =40 B; I _C =100 mA; P _D =330 mB _T ; h ₂₁ =100300; f _T >250 MFu	SOT23,SOD23	
L7	KST1623L7	SAMS	npn	V _{CB0} =50 B; I _C =100 mA; P _D =350 mBτ; h ₂₁ =300600; f _T >200 MΓu	SOT23,SOD23	
L7	MMBC1623L7	MOT	npn	V _{CB0} =50B; I _C =100 MA; P _D =300 MBT; h ₂₁ =300600	SOT23,SOD23	and the second second
L77	FMMTL717	ZETEX	pnp	V_{CB0} = 12 B; I_C = 1250 mA; P_D =500 mBT; h_{21} > 50; f_T =205 MFu,	S0T23,S0D23	7.007.00
L78	FMMTL718	ZETEX	pnp	V _{CBO} =20B; I _C =1000 мА; P _O =500 мВт; h ₂₁ >50; f _T =265 МГц	SOT23,SOD23	127.32 /2
L7p	BAT721	PHIL	shd	V _R <40 B; I _F <200 мA; V _F (I _F =100 мA)<0.42 B; I _R <15 мкA; C _D <50 пΦ	SOT23,SOD23	
L7t	BAT721	PHIL	shd	$V_R < 40 B$; $I_F < 200 \text{ mA}$; $V_F (I_F = 100 \text{ mA}) < 0.42 B$; $I_R < 15 \text{ m/A}$; $C_D < 50 \text{ n}\Phi$	SOT23,SOD23	
L7W	BAT721	PHIL	shd	$V_R < 40 \text{ B}; I_F < 200 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 0.42 \text{ B}; I_R < 15 \text{ mkA}; C_D < 50 \text{ n}\Phi$	SOT23,SOD23	A·n.c.·K
L8	BAR151	INF	pin×2	$V_R \le 100 \text{ B}; I_F \le 140 \text{ mA}; V_F \{I_F = 100 \text{ mA}\} \le 1.05 \text{ B}; I_R \le 0.1 \text{ mKA}; C_D \le 0.2 \text{ n}\Phi$	SOT23,SOD23	A1 · A2 · K1, A2
L8	KTC4075	KEC	non	V _{CB0} =60 B; I _C =150 мА; P _D =100 мВт; h ₂₁ =350700; f _T >80 МГц	SOT323,SC70	B-E-C
L8p	BAT721A	PHIL	shd×2	V _R <40 B; I _F <200 мA; V _F (I _F =100 мA)<0.42 B; I _R <15 мкA; C _D <50 пΦ	SOT23,SOD23	K1 · K2 · A1, A2
L8t	BAT721A	PHIL	shd×2	V _R <40 B; I _F <200 mA; V _F (I _F =100 mA)<0.42 B; I _R <15 mrA; C _D <50 nΦ	SOT23,SOD23	K1 · K2 · A1, A2
L8W	BAT721A	PHIL	shd×2	V _R <40 B; I _F <200 mA; V _F (I _F =100 mA)<0.42 B; I _R <15 mrA; C _D <50 nΦ	SOT23,SOD23	K1 • K2 • A1, A2
L9	1SS349	TOSH	shd	$V_B > 20B$; $V_E (I_E = 1A) < 0.55B$; $I_B (V_B = 20B) < 50$ m/A; $C_T < = 250$ n/ Φ	SOT346,SC59	A•n.c.•K
L9	BAR161	INF	pin×2	$V_B \le 100 B; I_E \le 140 mA; V_E (I_E = 100 mA) \le 1.05 B; I_B \le 0.1 mkA; C_D \le 0.2 n\Phi$	SOT23,SOD23	K1-K2-A1,A2
L9p	BAT721C	PHIL	shd×2	V _B <40 B; I _E <200 мА; V _E (I _E =100 мА)<0.42 B; I _B <15 мкА; С _D <50 пФ	SOT23,SOD23	A1-A2-K1,K2
L9t	BAT721C	PHIL	shd×2	V _B <40 B; I _E <200 mA; V _E (I _E =100 mA)<0.42 B; I _B <15 mκA; C _D <50 πΦ	SOT23,SOD23	A1-A2-K1,K2
L9W	BAT721C	PHIL	shd×2	V _B <40 B; I _E <200 mA; V _E (I _E =100 mA)<0.42 B; I _B <15 mκA; C _D <50 nΦ	SOT23,SOD23	A1-A2-K1.K2
LA	BF550	SIEM	pnp	V _{CR0} =40B; I _C =25 MA; P _D =280 MBT; h ₂₁ =50250; f _T =350 MFu	SOT23.SOD23	
LA	RN1442A	TOSH	Dnpn	V _{CBD} =50 B; I _C =300 MA; P _D =200 MBT; h ₂ =200700; f _T =30 MFu; R ₂ =10 KOM	SOT346,SC59	
LAo	BF550	PHIL	ono	V _{CB0} =40 B; I _C =25 MA; P _D =250 MBT; h ₂₁ >50; f _T =325 MFц	SOT23.SOD23	
LB	2SC2462B	REN	non	V _{CR0} =50B; I _C =100 MA; P _D =150 MBT; h ₂ :=100200	SOT23,SOD23	100,000,000,000
LB	2SC5850B	REN	non	V _{CB0} =50B;I _C =100 mA;P ₀ =150 mBr;h ₂₁ =100200	SOT323.SC70	Lot of the State o
LB	PN1442B	TOSH	Dnon	V _{CBO} =50B; I _C =300 мA; P _D =200 мBт; I _D =3501200; f _T =30 МГц; R ₁ =10 кОм	SOT346,SC59	200000000
LB	S525T	VISH	nMOS	V _{DS} -20B; I _D -30 MA; P _D -200 MBT; Q _F -16 MCM	SOT23,SOD23	
LBL	KTC4075	KEC	non	V _{CB0} =60B; I _C =150 мA; P _D =100 мBτ; y _F =16 мCм V _{CB0} =60B; I _C =150 мA; P _D =100 мBτ; h ₂₁ =350700; f _T >80 MFц	S0T323,SC70	
LBs	BF999	SIEM	nMOS		SOT23,SOD23	
LC	2SC2462C	REN	non	V _{DS} =20 B;I _D =30 мA;P _D =200 мВт;NF=1.0 дB;I _{DSS} =518 мA;Q _F =18мСм		
LC		REN	- specie	V _{CB0} =50B; I _C =100 mA; P _D =150 mBr; h ₂₁ =160320	SOT23,SOD23	
	2SC5850C	1.144	npn	V _{CB0} =50B; I _C =100 mA; P _D =150 mBr; h ₂₁ =160320	SOT323,SC70	1000000000
LD	2SC2462D	REN	npn	V _{CB0} =50B; I _C =100 mA; P _D =150 mBr; h ₂₁ =250500	SOT23,SOD23	
LD	2SC5850D	REN	npn	V _{CB0} =50B;I _C =100 mA;P _D =150 mBr;h ₂₁ =250500	SOT323,SC70	15
LD	BF543	TELEF	nMOS	V _{DS} =20B;I _O =30mA;P _O =200mBT;g _F =70mC;R _{OS(on)} =10 Om	SOT23,SOD23	
D3	BAT54S	ZOWIE	shd×2	V _R <30B;V _R (I _F =30мA)<500мB;C _D <10 пФ;t _{RR} <5 нс	SOT23,SOD23	
_Ds	BF543	SIEM	nMOS	V _{DS} =20 B;I _D =30 мA;P _D =200 мВт; NF=1.0 дВ; g _F =12 мСм	SOT23,SOD23	
LE	2SC2412KLNE	ROHM	npn	V_{C80} =50B; I_C =150 mA; P_D =200 mBT; h_{21} =390820; f_T >180 MFu	SOT346,SC59	100000000000000000000000000000000000000
LEp	BF660	PHIL	prijo	V _{CB0} =30 B; I _C =25 мA; P _D =280 мВт; h ₂₁ =30; f _T =650 МГц	SOT23,SOD23	1.015503102
LEs	BF660	SIEM	pnp	V _{CR0} =40 B; I _C =25 mA; P _D =280 mBT; h ₂₁ >30; f _T =700 MFu	SOT23,SOD23	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
LEs	BF660W	SIEM	pnp	V_{CB0} =40 B; I_C =25 MA; P_D =280 MBT; h_{21} >30; f_T =700 MFU	S0T323,SC70	B-E-C
LG	2SC2712GR	TOSH	npn	V _{CED} =50 B; I _C = 150 мА; P _D =150 мВт; h ₂₁ =200400; f _T >80 МГц	SOT346,SC59	B-E-C
LG	2SC4116	TOSH	npn	V_{CB0} =60 B; I_C =150 mA; P_D =100 mBr; h_{21} >200400; f_T >80 M Γ_{LL}	SOT323,SC70	B-E-C
LGR	KTC4075	KEC	npn	V _{CB0} =60 B; I _C = 150 мА; P _D =100 мВт; h ₂₁ =200400; f _T >80 МГц	SOT323,SC70	B-E-C
LGs	BF775A	SIEM	npn	V _{CB0} =25 B; I _C =30 мА; P ₀ =280 мВт; h ₂₁ =50250; f ₁ =5800 МГц	SOT23,SOD23	B·E·C
LH	BF569	TELEF	pnp	V _{CB0} =40 B; I _C =30 мA; P ₀ =200 мВт; h ₂₁ =2590 ; f ₁ >950 МГц	SOT23,SOD23	B-E-C
LHp	BF569	PHIL	npn	V _{GB0} =35 B; I _C =30 мА; P ₀ =280 мВт; h ₂₁ =50; f ₇ =900 МГц	SOT23,SOD23	B-E-C
LHs	BF569	SIEM	pnp	V _{GB0} =40 B; I _G =30 mA; P ₀ =280 mBt; h ₂₁ > 20; f ₇ > 950 MFu	SOT23,SOD23	B-E-C
LHs	BF569W	SIEM	pnp	V _{DB0} =40 B; I _C =30 мА; P ₀ =280 мВт; h ₂₁ > 20; f ₇ =950 МГц	SOT23,SOD23	B-E-C
LK	BF799	SIEM	npn	V _{GB0} =30 B; I _G =35 мА; P _D =280 мВт; h ₂₁ =40250; Г ₁ =1100 МГц	SOT23,SOD23	B-E-C
LKs	BF799W	SIEM	npn	V _{GB0} =30 B; I _G =35 MA; P ₀ =280 MBT; h ₂₁ =40250; f ₇ =1100 MF _Q	SOT323,SC70	B-E-C
LL	2SC2712BL	TOSH	npn	V _{CED} =50 B; I _C =150 мА; P _D =150 мВт; h ₂₁ =350700; f _T >80 МГц	SOT346,SC59	1750327555
LL	2SC4116	TOSH	npn	V _{CR0} =60 B; I _C =150 мА; P _D =100 мВт; h ₂₁ >350700; f ₁ >80 МГц	SOT323,SC70	120,537,007
LM	BF569R	TELEF	pnp	V _{CB0} =40 B; I _C =30 mA; P _D =200 mBr; h ₂₁ =2590.; f _T >950 MFu	SOT23.SOD23	1800/4 07
LO	2SC2712O	TOSH	ngn	V _{CF0} =50B; I _C =150 mA; P _D =150 mBT; h ₂₁ =70140; f ₇ >80 MFu	SOT346.SC59	2000
LO	2SC4116	TOSH	npn	V _{GBB} = 60 B; I _G = 150 мА; P _D = 100 мВт; h ₂₁ > 70 140; f _T > 80 МГц	SOT323.SC70	
LO	KTC4075	KEC	npn	V _{CP0} =60 B; I _C =150 мA; P _D =100 мВт; h ₂₁ =70140; f _T >80 МГц	SOT323.SC70	
LOs	BF775	SIEM	non	V _{CB0} =20 B; I _C =30 мA; P _D =280 мBт; h ₂₁ =40250; f ₁ =4500 МГц	SOT23,SOD23	100000000000000000000000000000000000000
LOs	BF775W	SIEM	nan	V _{CBB} =20 B; I _C =30 мА; P _D =280 мВт; h ₂₁ =40200; f _T =5000 МГц	SOT323.SC70	100/10/14/12/5
LR	2SC2412KLNR	ROHM	nan	V _{CBB} =50 B; I _C =150 mA; P _D =200 mB _T ; h ₂₁ =180390; f _T >180 MF _U	SOT346.SC59	TOUT OF
LRs	BF517	SIEM	non	V _{CB0} =20 B; I _C =25 мA; P _D =280 мB; I _{D2} =25250; I _T =2000 МГц	SOT23.SOD23	3222 28
LS	2SC2412KLNS	ROHM	npn	V _{CB0} =50 B; I _C =150 MA; P _D =200 MB1; h ₂₁ =270560; f _T >180 MF _U	SOT346,SC59	Li.
LSs	BF770A	SIEM	non	V _{CB0} =15 B;I _C =50 mA; P _D =300 mBt; h ₂₁ >40;f _T =5500 MFц	SOT23,SOD23	
LY	2SC2712Y	TOSH	_		SOT346,SC59	200
LY	2SC4116	TOSH	npn	V _{CED} =50 B; I _C =150 мA; P _D =150 мBτ; h ₂₁ =120240; f ₁ >80 MΓц	SOT323.SC70	-570.700.700
LY	KTC4075	KEC	npn	V _{GB0} =60 B; I _G =150 MA; P _D =100 MBr; h ₂₁ >120240; f _T >80 MFu		
M1	100,000,000		npn	V _{GB0} =60 B; I _C =150 мA; P _D =100 мBт; h ₂₁ =120240; f _T >80 МГц	SOT323,SC70	
	MMBZ5256BT	DIODS	dz	V ₂ (I _{2T} =4.2 mA)=28.531.5 B; I _R <0.1 mkA	SOT523	A·n.c.·K
M16	PMBF4416A	PHIL	nFET	V _{DS} =35B;I _{DSS} =15MA;P _D =250 MBT;g _F <7.5 MCM	SOT23,SOD23	
M1B	MMBT2222ALT1	ON	npn	V _{GB0} =60 B; I _C =600 MA; P _D =225 MBT; h ₂₁ >30	SOT23,SOD23	200000000000000000000000000000000000000
M1E	MMBTA43LT1	MOT	npn	V _{сво} =200 B; I _c =500 мА; P _D =225 мВт; h ₂₁ >25; f ₁ >50 МГц	SOT23,SOD23	100000000
M1J	MMBT2369LT1	MOT	npn	V _{CB0} =40 B; I _C =200 мА; P ₀ =300 мВт; h ₂₁ =40120	SOT23,SOD23	
M1p	BFR30	PHIL	nFET	V _{DS} =25B;I _{DSS} =10mA;P _D =250mBT;g _F =4mCm	SOT23,SOD23	
M1T	ADM1811-10AKS	-	mrc	V _{TR} =4.35B; V _{DD} =15.5B; I _{CC} <16 мкА	SOT323,SC70	90
MIT	ADM1811-10ART	AD	mrc	V _{TR} =4.35B; V _{DD} =15.5B; I _{CC} <16 мкА	SOT23,SOD23	
MIV	ADM1811-5AKS	AD	mrc	V _{тн} =4.62B; V _{DD} =15.5B; I _{CC} <16 мкА	SOT323,SC70	
MIV	ADM1811-5ART	AD	mrc	V _{TR} =4.62B; V _{DD} =15.5B; I _{CC} <16 мкА	SOT23,SOD23	50
M2	MMBZ5257BT		dz	V _Z (I _{ZT} =3.8 mA)=31.3534.65B; I _R <0.1 mrA	The state of the s	A·n.c.·K
M2C	MMBTA70LT1	MOT	pnp	V_{CED} =40 B; I_C = 100 мA; P_D =300 мВт; h_{21} =40400; f_T > 125 МГц	SOT23,SOD23	
M2p	BFR31	PHIL	nFET	V _{DS} =25B;I _{DSS} =5мA;P _D =250мВт; g _F =4.5мСм	SOT23,SOD23	0.0000000000000000000000000000000000000
M3	KDV173	KEC	pin×2	V _R =50B;I _R =0.1 мкА; С _Т =0.25 пФ; R _S <7.00м	SOT23,SOD23	
M3	KST812M3	SAMS	pnp	V _{GB0} =50 B; I _C = 100 mA; P _D =350 mBT; h ₂₁ =60120	SOT23,SOD23	
M3	MMBA812M3	SAMS	pnp	V _{GB0} =50 B; I _C = 100 мА; P _D =350 мВт; h ₂₁ =60120	SOT23,SOD23	
M3	MMBA812M3	MOT	pnp	V _{CB0} =50 B; I _C =100 mA; P _D =350 mBr; h ₂₁ =60120	SOT23,SOD23	B-E-C
M3	MMBZ5258BT	DIODS	dz	V ₂ (I _{ZT} =3.4 mA)=34.237.8 B; I _R <0.1 mkA	SOT523	A•n.c.•K
МЗА	MMBTH24LT1	MOT	npn	V_{CB0} =40 B; I_C =50 мA; P_D =300 мВт; h_{21} >30; f_T >400 МГц	SOT23,SOD23	B-E-C
МЗВ	MMBT918LT1	MOT	npn	V_{CB0} =30 B; I_C =50 mA; P_D =300 mBt; h_{21} >20; f_T >600 MFu	SOT23,SOD23	B-E-C
M3J	MMBTH69LT1	MOT	pnp	V _{CB0} =15 B; P _D =300 мВт; h ₂₁ =30300; f _T >2000 МГц	SOT23,SOD23	B·E·C
МЗр	BFT46	PHIL	nFET	V _{DS} =25B; I _{DSS} =1.5 mA; P _D =250 mBT; g _F >0.5 mCm	SOT23,SOD23	D·S·G
мзт	ADM1813-10AKS	AD	mrc	V _{TR} =4.35B; V _{DD} =15.5B; I _{CC} <16 mKA	SOT323,SC70	V _{cc} •RST•GND
M3T	ADM1813-10ART	AD	mrc	V _{TR} =4.35B; V _{DD} =15.5B; I _{DD} <16 mkA	SOT23,SOD23	RST+V _{cc} +GND
M3V	ADM1813-5AKS	AD	mrc	V _{TB} =4.62B; V _{DD} =15.5B; I _{DD} <16 мкА	SOT323.SC70	
M3V	ADM1813-5ART	AD	mrc	V _{TB} =4.62B; V _{DD} =15.5B; I _{DD} <16 мкА	SOT23,SOD23	





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
M4	BSR56	FAIR	nFET	V _{DS} =40B; I _D =50 mA; P _D =250 mBt; R _{DS(on)} < 25 Om	SOT23,SOD23	D·S·G
M4	KSTB12M4	SAMS	pnp	V _{CB0} =50B; I _C =100 mA; P _D =350 mBT; h ₂₁ =90180	SOT23,SOD23	B·E·C
M4	MMBA812M4	MOT	pnp	V _{CB0} =50B; I _C =100 mA; P ₀ =350 mBt; h ₂₁ =90180	SOT23,SOD23	B·E·C
M4	MMBZ5259BT	DIODS	dz	V ₇ (I ₇₇ =3.2mA)=37.0541.0 B; I _B <0.1 mkA	SOT523	A+n.c.+K
M4A	MMBV109LT1	MOT	var	V _B >30 B; I _E =200 мА; С _{3.B} =2632 пФ; С _{3.B} /С _{25.B} =5.06.5	SOT23,SOD23	A+n.c.+K
M4B	MMBV432LT1	ON	var×2	V _B >14B;I _F =200 мА; С _{2 B} =4348.1 пФ; С _{2 B} /С _{8 B} =1.52	SOT23,SOD23	A1-A2-K1,K2
M4C	MMBV3102LT1	ON	var	V _B >30 B; I _F =200 мА; С _{3 B} =2025 пФ; С _{2 B} /С _{25 B} =4.54.8	SOT23,SOD23	A+n.c.+K
M4E	MMBV105GLT1	ON	var	V _B >30 B; I _F =200 mA; C _{3 B} /C _{25 B} =4.06.5	S0T23,S0D23	A·n.c.·K
M4F	ADM 1815- 10AKSZ	AD	mrc	V_{TR} = 2.88 B; V_{DD} =15.5B; I_{CC} <16 MKA	S0T323,SC70	V _{CC} •RST•GND
M4F	ADM 1815- 10ARTZ	AD	mrc	V_{TR} = 2.88 B; V_{CD} =15.5 B; I_{CC} < 16 MKA	SOT23,SOD23	RST•V _{CC} •GND
M4F	MMBD353LT1	MOT	shd×2	$V_B > 7B$; $V_E (I_E = 10 \text{ MA}) < 0.6B$; $C_T < 1 \text{ m}\Phi$	S0T23,S0D23	K1-A2-A1,K2
M4G	MMBV2101LT1	MOT	var	V _R >30 B; I _F =200 мA; C _{4 B} =6.17.5 nΦ; C _{2 B} /C _{30 B} =2.53.2	SOT23,SOD23	A+n.c.+K
M4P	BSR56	PHIL	nFET	V _{DS} =40B; I _D =50 mA; P _D =250 mBr; R _{DS(on)} < 25 Om	SOT23,SOD23	D·S·G
M4T	ADM 1818-5AKSZ	AD	mrc	V _{TR} =3.06 B; V _{DD} =15.5 B; I _{DC} <16 mrA	S0T323,SC70	V _{CC} •RST•GND
M4T	ADM1818-5ARTZ	AD	mrc	V _{TB} =3.06 B; V _{DD} =15.5 B; I _{DD} <16 mrA	SOT23,SOD23	RST • V _{CC} • GND
M4Y	ADM 1810-5AKSZ	AD	mrc	V _{TR} =4.62 B; V _{DD} =15.5 B; I _{DC} <16 mrA	S0T323,SC70	V _{CC} •RST•GND
M4Y	ADM 1810-5ARTZ	AD	mrc	V _{TR} =4.62 B; V _{DD} =15.5 B; I _{DC} <16 мкA	SOT23,SOD23	RST • V _{CC} • GND
M4Z	ADM 1810- 10AKSZ	AD	mrc	V _{TR} =4.35 B; V _{DD} =15.5B; I _{CC} <16 мкA	S0T323,SC70	V _{CC} •RST•GND
M4Z	ADM 1810- 10ARTZ	AD	mrc	V _{TR} =4.35 B; V _{DD} =15.5 B; I _{DC} <16 мкА	SOT23,SOD23	RST•V _{CC} •GND
M5	KST812M5	SAMS	pnp	V _{CB0} =50B; I _C =100 mA; P _D =350 mBt; h ₂₁ =135270	SOT23,SOD23	B·E·C
M5	MMBA812M5	SAMS	pnp	V _{CB0} =50B; I _C =100 mA; P _D =350 mBt; h ₂₁ =135270	SOT23,SOD23	B·E·C
M5	MMBA812M5	MOT	pnp	V _{CB0} =50B; I _C =100 mA; P _D =350 mBT; h ₂₁ =135270	S0T23,S0D23	B·E·C
M5	MMBD352WT1	MOT	shd×2	$V_B > 7B$; $V_F (I_F = 10 \text{ mA}) < 0.6B$; $C_T < 1 \text{ m}\Phi$	SOT323,SC70	A1-K2-A2,K1
M54	ADM 1816- 10AKSZ	AD	mrc	V _{TR} = 2.88 B; V _{DD} = 15.5 B; I _{CC} < 16 mrA	SOT323,SC70	V _{CC} •RST•GND
M54	ADM1816- 10ARTZ	AD	mrc	V _{TR} = 2.88 B; V _{DD} =15.5 B; I _{CC} <16 мкА	SOT23,SOD23	RST•V _{CC} •GND
M59	ADM 1818- 20AKSZ	AD	mrc	V _{TR} = 2.55 B; V _{CD} = 1 5.5 B; I _{CC} < 16 мкA	S0T323,SC70	
M59	ADM 1818- 20ARTZ	AD	mrc	V _{TR} =2.55 B;V _{DD} =15.5 B; I _{CC} <16 mrA	SOT23,SOD23	RST+V _{CC} +GND
M5A	ADM1815-20AKS	AD	mrc	V _{TR} =2.55 B; V _{CD} =15.5 B; I _{CC} <16 мкА	S0T323,SC70	00
M5A	ADM1815-20ART	AD	mrc	V _{TR} =2.55 B; V _{DD} =15.5 B; I _{CC} <16 мкА	SOT23,SOD23	- 00
M5B	ADM 1815- R22AKS	AD	mrc	V _{TR} =2.18 B; V _{DD} =15.5 B; I _{CC} <16 мкA	S0T323,SC70	
M5B	ADM1815- R22ART	AD	mrc	V_{TR} =2.18 B; V_{DD} =15.5B; I_{CC} <16 MKA	SOT23,SOD23	***************************************
M5C	ADM 1815- R23AKS	AD	mrc	V _{TR} =2.31 B;V _{DD} =15.5 B; I _{CC} <16 мкA	S0T323,SC70	
M5C	ADM 1815- R23ART	AD	mrc	V _{TR} =2.31 B;V _{DD} =15.5 B;I _{DC} <16 мкA	SOT23,SOD23	855
M5C	MMBD7000LT1	MOT	di×2	$V_B > 100 B; I_F < 200 \text{mA}; V_F (I_F = 100 \text{mA}) < 1.1 B; C_D < 1.5 \text{n} \Phi; t_{BR} < 4 \text{Hc}$	SOT23,SOD23	
M5E	ADM 1815-10AKS	AD	mrc	V _{TR} =2.88 B; V _{CD} =15.5 B; I _{CC} <16 мкА	S0T323,SC70	V _{CC} •RST•GND
M5E	ADM 1815-10ART	AD	mrc	V _{TR} =2.88 B; V _{DD} =15.5 B; I _{CC} <16 мкA	SOT23,SOD23	- 00
M5G	MMBD352LT1	MOT	shd×2	V _B >7B;V _F (I _F =10 мA)<0.6B;C _T <1 пФ	SOT23,SOD23	
M5K	ADM1815-5AKS	AD	mrc	V _{TR} =3.06 B; V _{DD} =15.5 B; I _{CC} <16 мкА	SOT323,SC70	V _{CC} •RST•GND
M5K	ADM1815-5ART	AD	mrc	V _{TR} =3.06 B; V _{DD} =15.5 B; I _{DC} <16 мкА	SOT23,SOD23	RST V _{CC} GND
M5P	BSR57	PHIL	nFET	V _{DS} =40B; I _D =20 mA; P _D =250 mBt; R _{DS(on)} <40 Om	SOT23,SOD23	D·S·G
M6	BSS66	ZETEX	npn	V _{C80} =60 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =50150; f _T >250 МГц	SOT23,SOD23	B·E·C
M6	KST812M6	SAMS	pnp	V _{CB0} =50 B; I _C =100 mA; P _D =350 mBT; h ₂₁ =200400	SOT23,SOD23	B·E·C
M6	MMBA812M6	SAMS	onp	V _{CR0} =50B; I _C =100 mA; P _D =350 mBT; h ₂₁ =200400	SOT23,SOD23	B·E·C

Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3
M6	MMBA812M6	MOT	pnp	V _{CB0} =50 B; I _C =100 mA; P _D =350 mBT; h ₂₁ =200400	SOT23,SOD23	B-E-C
M68	PMBFJ210	PHIL	nFET	V _{DS} =25B;I _{DSS} =215мA;P _D =250мBт;g _F =412мСм	SOT23,SOD23	S·D·G
M69	PMBFJ211	PHIL	nFET	V _{DS} =25B;I _{DSS} =720мA;P _D =250мBт;g _E =612мСм	SOT23,SOD23	S·D·G
M6A	ADM1816-20AKS	AD	mrc	V _{тв} =2.55B; V _{по} =15.5B; I _{сс} <16 мкА	SOT323,SC70	V _{cc} •RST•GND
M6A	ADM1816-20ART	AD	mrc	V _{TB} =2.55B; V _{DD} =15.5B; I _{DD} <16 MKA	SOT23,SOD23	RST-V _{cc} -GND
M6B	ADM1816- R22AKS	AD	mrc	V _{TR} =2.18B; V ₀₀ =15.5B; I _{CC} <16 m/cA	SOT323,SC70	V _{CC} •RST•GND
M6B	ADM1816- R22ART	AD	mrc	V _{TR} =2.18B; V _{DD} =15.5B; I _{CC} <16 mKÅ	SOT23,SOD23	RST-V _{CC} -GND
M6C	ADM1816- R23AKS	AD	mrc	V _{TB} =2.31B; V ₀₀ =15.5B; I _{CC} <16 m/cA	SOT323,SC70	V _{CC} +RST+GND
M6C	ADM1816- R23ART	AD	mrc	V _{TB} =2.31B; V ₀₀ =15.5B; I _{CC} <16 мкA	SOT23,SOD23	RST-V _{CC} -GND
M6E	ADM1816-10AKS	AD	mrc	V _{TR} =2.88B; V _{DD} =15.5B; I _{CC} <16 мкA	SOT323,SC70	
M6E	ADM1816-10ART	AD	mrc	V _{TR} =2.88B; V _{DD} =15.5B; I _{CC} <16 мкA	SOT23,SOD23	RST-V _{cc} -GND
М6Н	ADM1816- 20AKSZ	AD	mrc	V _{TR} =2.55B; V ₀₀ =15.5B; I ₀₀ <16 мкА	SOT323,SC70	V _{CC} •RST•GND
М6Н	ADM1816- 20ARTZ	AD	mrc	V _{TR} =2.55B; V ₀₀ =15.5B; I _{CC} <16 мкА	SOT23,SOD23	RST+V _{cc} +GND
М6Н	MMBD354LT1	MOT	shd×2	$V_R > 7 B_t V_E (I_E = 10 \text{ MA}) < 0.6 B_t C_T < 1 \text{ m}$	SOT23,SOD23	A1 • A2 • K1, K2
M6K	ADM1816-5AKS	AD	mrc	V _{TR} =3.06B; V _{DD} =15.5B; I _{CC} <16 мкA	SOT323,SC70	V _{CC} •RST•GND
M6K	ADM1816-5ART	AD	mrc	V _{TR} =3.06B; V _{DD} =15.5B; I _{CC} <16 мкА	SOT23,SOD23	RST-V _{CC} -GND
M6P	BSR58	PHIL	nFET	V _{DS} =40B;I _D =8 mA;P _D =250 mBt;R _{DS(m)} <60 Om	SOT23,SOD23	D·S·G
М6Х	ADM1813-5AKSZ	AD	mrc	V _{TR} =4.62B; V _{DD} =15.5B; I _{CC} <16 mKA	SOT323,SC70	V _{CC} •RST•GND
M6X	ADM1813-5ARTZ	AD	mrc	V _{TR} =4.62B; V _{DD} =15.5B; I _{CC} <16 mKA	SOT23,SOD23	RST+V _{CC} +GND
M6Y	ADM1813- 10AKSZ	AD	mrc	V _{TR} =4.35B; V ₀₀ =15.5B; I _{CC} <16 мкА	SOT323,SC70	V _{CC} •RST•GND
M6Y	ADM1813- 10ARTZ	AD	mrc	V _{TR} =4.35B; V ₀₀ =15.5B; I _{CC} <16 мкА	SOT23,SOD23	RST+V _{CC} +GND
M6Z	ADM1811-5AKSZ	AD	mrc	V _{TR} =4.62B; V _{DD} =15.5B; I _{CC} <16 мкА	SOT323,SC70	V _{CC} •RST•GND
M6Z	ADM1811-5ARTZ	AD	mrc	V _{TR} =4.62B; V _{DD} =15.5B; I _{CC} <16 мкA	SOT23,SOD23	RST+V _{cc} +GND
M7	BSS67	ZETEX	npn	V_{CB0} =60 B; I_C =100 mA; P_D =330 mB1; h_{21} =100300; f_T >300 M Γ_U	SOT23,SOD23	B·E·C
M7	KST812M7	SAMS	pnp	V _{CB0} =50 B; I _C =100 mA; P _D =350 mBT; h ₂₁ =300600	SOT23,SOD23	B·E·C
M7	MMBA812M7	SAMS	pnp	V _{CB0} =50 B; I _C = 100 мA; P _D =350 мBт; h ₂₁ =300600	SOT23,SOD23	B·E·C
M7.	MMBA812M7	MOT	pnp	V _{GB0} =50 B; I _G =100 мА; P _D =350 мВт; h ₂₁ =300600	SOT23,SOD23	B·E·C
M70	ADM1811- 10AKSZ	AD	mrc	V _{тв} =4.35B; V ₀₀ =15.5B; I _{CC} <16 мкА	SOT323,SC70	V _{CC} •RST•GND
M70	ADM1811- 10ARTZ	AD	mrc	V _{TR} =4.35B; V ₀₀ =15.5B; I _{CC} <16 мкА	SOT23,SOD23	RST-V _{CC} -GND
M70	PMBFJ212	PHIL	nFET	V _{DS} =25B;I _{DSS} =1540 mA;P _D =250 mBT; g _F =712 mCm	SOT23,SOD23	S·D·G
M71	ADM1812- 10AKSZ	AD	mrc	V _{TR} =4.35B; V ₀₀ =15.5B; I _{CC} <16 m/cA	SOT323,SC70	V _{CC} +RST+GND
M71	ADM1812- 10ARTZ	AD	mrc	V _{TR} =4.35B; V ₀₀ =15.5B; I _{CC} <16 мкА	SOT23,SOD23	RST-V _{CC} -GND
M72	ADM1812-5AKSZ	AD	mrc	V _{TR} =4.62B; V _{DD} =15.5B; I _{CC} <16 mKA	SOT323,SC70	V _{CC} •RST•GND
M72	ADM1812-5ARTZ	AD	mrc	V _{TR} =4.62B; V _{DD} =15.5B; I _{CC} <16 mKA	SOT23,SOD23	RST+V _{CC} +GND
M73	ADM1815-5AKSZ	AD	mrc	V _{TR} =3.06B; V _{DD} =15.5B; I _{CC} <16 mkA	SOT323,SC70	V _{CC} •RST•GND
M73	ADM1815-5ARTZ	AD	mrc	V _{TR} =3.06B; V _{DD} =15.5B; I _{CC} <16 mKA	SOT23,SOD23	
M74	ADM1815- R22AKSZ	AD	mrc	V _{TB} =2.18B; V _{DD} =15.5B; I _{CC} <16 mKA	SOT323,SC70	V _{CC} +RST+GND
M74	ADM1815- R22ARTZ	AD	mrc	V _{TR} =2.18B; V _{DD} =15.5B; I _{CC} <16 mKA	SOT23,SOD23	RST+V _{CC} +GND
M75	ADM1815- R23AKSZ	AD	mrc	V _{TR} =2.31B; V _{DD} =15.5B; I _{CC} <16 мкА	SOT323,SC70	V _{cc} +RST+GND
M75	ADM1815- B23ARTZ	AD	mrc	V _{TR} =2.31B; V ₀₀ =15.5B; I _{CC} <16 мкА	SOT23,SOD23	RST+V _{CC} +GND





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
M76	ADM 1815- 20AKSZ	AD	mrc	V _{TR} =2.55 B; V _{DD} =15.5 B; I _{CC} <16 мкА	S0T323,SC70	V _{CC} •RST•GND
M76	ADM 1815- 20ARTZ	AD	mrc	V _{TR} =2.55 B; V _{CO} =15.5 B; I _{CC} <16 мкA	SOT23,SOD23	RST•V _{oc} •GND
M77	ADM1816-5AKSZ	AD	mrc	V _{TR} =3.06 B; V _{DD} =15.5 B; I _{CC} <16 mKA	SOT323,SC70	V _{CC} •RST•GND
M77	ADM 1816-5ARTZ	AD	mrc	V _{TR} =3.06 B; V _{DD} =15.5 B; I _{CC} <16 mKA	SOT23,SOD23	RST • V _{CC} • GND
M78	ADM 1816- R22AKSZ	AD	mrc	V _{TR} =2.18 B; V _{DD} =15.5 B; I _{CC} <16 мкA	SOT323,SC70	V _{cc} •RST•GND
M78	ADM1816- R22ARTZ	AD	mrc	V _{TR} =2.18 B; V ₀₀ =15.5 B; I _{CC} <16 mrA	SOT23,SOD23	RST+V _{CC} +GND
M79	ADM1816- R23AKSZ	AD	mrc	V _{TR} =2.31 B; V _{DD} =15.5 B; I _{CC} <16 mrA	S0T323,SC70	V _{CC} •RST•GND
M79	ADM1816- R23ARTZ	AD	mrc	V _{TR} =2.31 B;V _{DD} =15.5B; I _{DC} <16 mrA	SOT23,SOD23	RST•V _{CC} •GND
M7A	ADM1817-20AKS	AD	mrc	V _{TR} = 2.55 B; V _{DD} =15.5 B; I _{DC} <16 мкА	SOT323,SC70	V _{CC} •RST•GND
M7A	ADM1817-20ART	AD	mrc	V _{TR} =2.55 B; V _{DD} =15.5 B; I _{DC} <16 мкА	SOT23,SOD23	RST • V _{CC} • GND
M7B	ADM1817- R22AKS	AD	mrc	V _{TR} =2.18 B; V _{CD} =15.5 B; I _{CC} <16 мкA	S0T323,SC70	V _{CC} •RST•GND
M7B	ADM 1817- R22ART	AD	mrc	V _{TR} =2.18 B; V _{DD} =15.5 B; I _{CC} <16 mrA	SOT23,SOD23	
M7C	ADM1817- R23AKS	AD	mrc	V _{TR} =2.31 B; V _{DD} =15.5 B; I _{DC} <16 mrA	S0T323,SC70	55
M7C	ADM1817- R23ART	AD	mrc	V _{TR} =2.31 B; V _{DD} =15.5 B; I _{DC} <16 m/A	SOT23,SOD23	RST-V _{CC} -GND
M7E	ADM 1817-10AKS	AD	mrc	V _{TR} =2.88 B; V _{DD} =15.5 B; I _{DC} <16 мкA	SOT323,SC70	V _{CC} •RST•GND
M7E	ADM 1817 - 10ART	AD	mrc	V _{TR} = 2.88 B; V _{DD} =15.5 B; I _{CC} < 16 мкA	SOT23,SOD23	RST+V _{CC} +GND
M7F	ADM1817-5AKSZ	AD	mrc	V _{TR} =3.06 B; V _{DD} =15.5 B; I _{DC} <16 мкА	SOT323,SC70	V _{CC} •RST•GND
M7F	ADM 1817-5ARTZ	AD	mrc	V _{TR} =3.06 B; V _{DD} =15.5 B; I _{DD} < 16 мкА	S0T23,S0D23	RST-V _{CC} -GND
M7G	ADM 1817- 10AKSZ	AD	mrc	V _{тп} =2.88 B; V ₀₀ =15.5 B; I _{ос} <16 мкА	S0T323,SC70	V _{oc} •RST•GND
M7G	ADM1817- 10ARTZ	AD	mrc	V _{TR} = 2.88 B; V _{DD} =15.5 B; I _{DD} <16 m/A	SOT23,SOD23	RST+V _{CC} +GND
M7H	ADM1817- 20AKSZ	AD	mrc	V _{TR} =2.55 B; V _{DD} =15.5 B; I _{CC} <16 мкA	SOT323,SC70	
M7H	ADM 1817- 20ARTZ	AD	mrc	V _{ТR} =2.55 B;V _{DD} =15.5B;I _{CC} <16 мкА	SOT23,SOD23	
M7J	ADM1817- R22AKSZ	AD	mrc	V _{TR} =2.18 B;V _{0D} =15.5B; I _{CC} <16 мкА	S0T323,SC70	"
M7J	ADM1817- R22ARTZ	AD	mrc	V _{тр} =2.18 B; V ₀₀ =15.5B; I _{ос} <16 мкА	SOT23,SOD23	
M7K	ADM1817-5AKS	AD	mrc	V _{TR} =3.06 B; V _{DD} =15.5 B; I _{CC} < 16 мкA	S0T323,SC70	
M7K	ADM 1817-5ART	AD	mrc	V _{TR} =3.06 B; V _{DD} =15.5 B; I _{CC} <16 mrA	SOT23,SOD23	
M7L	ADM1817- R23AKSZ	AD	mrc	V _{TR} =2.31 B; V _{CO} =15.5 B; I _{CC} <16 мкA	S0T323,SC70	
M7L	ADM1817- R23ARTZ	AD	mrc	V _{TR} =2.31 B; V _{DD} =15.5B; I _{CC} <16 мкA	SOT23,SOD23	
M7N	ADM1818- R23AKS	AD	mrc	V _{TR} =2.31 B; V _{CO} =15.5B; I _{CC} <16 мкA	SOT23,SOD23	.000
M7N	ADM1818- R23AKSZ	AD	mrc	V _{TR} =2.31 B; V _{CO} =15.5 B; I _{CC} <16 мкA	S0T323,SC70	**
M7P	ADM1818- 10AKSZ	AD	mrc	V _{TR} =2.88 B; V _{DD} =15.5 B; I _{CC} <16 m/cA	S0T323,SC70	
M7P	ADM 1818- 10ARTZ	AD	mrc	V _{TR} =2.88 B; V _{DD} =15.5B; I _{DC} <16 мкA	SOT23,SOD23	
M8	BSH103	PHIL		V _{DS} =30B;I _D =850mA;P _D =500mBT;P _{DS(on)} <0.50m	SOT23,SOD23	
M8	BSS66R	ZETEX	npn	V _{CB0} =60 B; I _C =100 мA; P _D =330 мВт; h ₂₁ =50150; f _T >250 МГц	S0T23,S0D23	
M8A	ADM 1818-20AKS	AD	mrc	V _{TR} = 2.55 B; V _{DD} = 15.5 B; I _{CC} < 16 мкA	S0T323,SC70	
M8A	ADM 1818-20ART	AD	mrc	V _{TR} = 2.55 B; V _{DD} =15.5 B; I _{CC} < 16 мкA	SOT23,SOD23	RST-V _{CC} -GND

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
M8B	ADM1818- R22AKS	AD	mrc	V _{TR} =2.18B; V _{DD} =15.5B; I _{CD} <16 мкA	SOT323,SC70	V _{CC} •RST•GND
M8C	ADM 1818- R22AKSZ	AD	mrc	V_{TR} =2.18B; V_{00} =15.5B; I_{CC} <16 mrA	SOT323,SC70	V _{CC} +RST+GND
M8C	ADM1818- R22ART	AD	mrc	V _{TR} =2.18B; V _{DD} =15.5B; I _{CC} <16 mrA	SOT23,SOD23	RST+V _{CC} +GND
M8C	ADM 1818- R23ART	AD	mrc	V _{TR} =2.31B; V ₀₀ =15.5B; I _{CC} <16 mrA	SOT323,SC70	V _{CC} •RST•GND
M8E	ADM1818-10AKS	AD	mrc	V _{TR} =2.88B; V _{DD} =15.5B; I _{CC} <16 m/cA	S0T323,SC70	V _{CC} +RST+GND
M8E	ADM1818-10ART	AD	mrc	V _{TB} =2.88B; V _{DD} =15.5B; I _{CC} <16 мкА	SOT23,SOD23	RST+V _{CC} +GND
M8E	ADM1818-5AKS	AD	mrc	V _{TR} =3.06B; V _{DD} =15.5B; I _{CC} <16 мкА	SOT323,SC70	V _{CC} •RST•GND
M8K	ADM1818-5ART	AD	mrc	V _{TR} =3.06B; V _{DD} =15.5B; I _{CC} <16 m/cA	SOT23,SOD23	RST-V _{CC} -GND
М8р	BSN20	PHIL	nMOS	V _{DS} =50B;I _D =110 мA	SOT23,SOD23	G·S·D
M9	BSS67R	ZETEX	npn	V_{CB0} =60 B; I_C =100 mA; P_D =330 mBr; h_{24} =100300; f_T >300 MF $_{II}$	SOT23,SOD23	B-E-C
MA	FMMTA06R	ZETEX	non	V_{CR0} =80 B; I_C =500 mA; P_D =330 mBr; h_{21} >50; f_T >100 MFu	SOT23,SOD23	B-E-C
MA	M 1MA 151AT	MOT	di	V _B < 40 B; I _E < 100 mA	S0T346,SC59	K•n.c.•A
MA6	MMBD2838LT1	MOT	di×2	V _B <50 B; I _E <150 mA; V _E (I _E =50 mA)<1 B; C _D <4 nΦ; t _{BB} <4 hc	SOT23,SOD23	A1-A2-K1,K2
MB	2SA1052B	REN	ono	V _{GB0} =30 B; I _C =100 MA; P _D =150 MBT; h ₂₁ =100200	SOT23,SOD23	B-E-C
MB	FMMTA56R	ZETEX	gng	V _{CR0} =80 B; I _C =500 mA; P _D =330 mBt; h ₂₁ >50; f _T >100 MFu	SOT23,SOD23	B-E-C
мв	M 1MA 152AT	MOT	di	V _B < 80 B; I _E < 100 mA	SOT346.SC59	115531 37
MC	2SA1052C	REN	ono	V _{СВО} =30 B; I _C =100 мА; P _D =150 мВт; h ₂₁ =160320	SOT23.SOD23	
MC	2SA2080C	REN	ono	V _{GR0} =30 B; I _G =100 mA; P _D =150 mBT; h ₂₁ =160320	SOT323.SC70	
MC	ZVN3306F	ZETEX	nMOS	V _{DS} =60 B; I _D =150 mA; P _D =330 mBT; g _F =100 mCm; R _{DS(an)} =5 0m	SOT23,SOD23	
MCs	BFS17P	SIEM	ngn	V _{CB0} =25 B; I _C =25 MA; P _G =280 MBT; h ₂₁ =20150; f _T =2500 MFu	SOT23,SOD23	
MCs	BFS17W	SIEM	npn	V _{при} =25 B; I _n =50 мА; Р _п =280 мВт; h21s=20150; I _T >2500 МГц	SOT323,SC70	Tale of the same o
MD	2SA1052D	REN	ono	V _{CR0} =30 B; I _C =100 MA; P _D =150 MBT; h ₂₁ =250500	SOT23.SOD23	125.17. 37
MD	2SA2080D	REN	ono	V _{CR0} =30 B; I _C =100 MA; P _D =150 MBT; h ₂₁ =250500	SOT323,SC70	T(4T, 5)
MF	ZVN3310F	ZETEX	nMOS	V _{DS} =100B; I _D =100 мA; P _D =330 мBт; g _F =150 мСм; R _{DSfool} =5 Ом	SOT23.SOD23	
MH	M1MA141KT	MOT	di	V _B <40 B:I _C <100 MA	SOT323.SC70	
MH	M 1MA 151KT	MOT	di	V _B <40 B; I _F <100 mA	SOT346.SC59	100000000000000000000000000000000000000
MI	M 1MA 142KT	MOT	di	V _B <80 B; I _F <100 mA	SOT323,SC70	100 100 100 100 100 100 100 100 100 100
MI	M 1MA 142KT	MOT	di	V _R <80 B; I _F <100 mA	SOT346,SC59	
MJ1	MMBD355LT1	MOT	shd×2	V _R >7 B; V _E (_E =10 MA) < 0.6B; C _T <1 πΦ	SOT23.SOD23	
ML	ZVP3306F	ZETEX			SOT23,SOD23	100
MN	M1MA141WA	MOT	dix2	V _{DS} =60 B; I _D =90 mA; P _D =330 mBT; g _F =25 mCm; R _{DS(on)} =80 Om	SOT323.SC70	Lance Contract Contra
MN				V _B <40 B; I _F <100 mA		
	M1MA151WA	MOT	di×2	V _R <40 B;I _F <100 mA	SOT346,SC59	100000000000000000000000000000000000000
MO	M 1MA 142WA	MOT	di×2	V _B <80 B; I _F <100 mA	SOT323,SC70	100
MO	M1MA152W	MOT	dix2	V _R <80 B; I _F <100 mA	SOT346,SC59	100
MR	ZVP3310F	ZETEX	pMOS	V _{DS} = 100B; I _D =45 мA; P _D =330 мBr; g _F =60 мСм; R _{DS(cn)} =14 0м	SOT23,SOD23	100 C
MT	M1MA141WK		di×2	V _R <40 B; I _F <100 mA	SOT323,SC70	
MT	M1MA151WK	MOT	di×2	V _R <40 B;I _F <100 mA	SOT346,SC59	
MT	ZVP1320F	ZETEX	pMOS	V _{DS} =200B;I _D =35 мA;P _D =330 мВт; g _F =150 мСм; R _{DS(on)} =2.5 Ом	SOT23,SOD23	2
МП		AD	mrc	V _{TR} =4.35B; V _{DD} =15.5B; I _{CC} <16 mкA	SOT323,SC70	40
МП	ADM1812-10ART	AD	mrc	V _{TR} =4.35B; V _{DD} =15.5B; I _{CC} <16 mrA	SOT23,SOD23	- 10
MTV	ADM1812-5AKS	AD	mrc	V _{TR} =4.62B; V _{DD} =15.5B; I _{CC} <16 mrA	SOT323,SC70	w
MTV	ADM1812-5ART	AD	mrc	V _{TR} =4.62B; V ₀₀ =15.5B; I _{CC} <16 m;A	SOT23,SOD23	
MU	M1MA142WK	MOT	di×2	V _R <80 B; I _F <100 mA	SOT323,SC70	
MU	M 1MA 152WK	MOT	di×2	V _R <80 B;I _F <100 mA	SOT346,SC59	
MU	ZVN3320F	ZETEX	nMOS	V _{DS} =200B; I _D =60 мA; P _D =330 мВт; g _F =100 мСм; R _{DS(an)} =10 Ом	SOT23,SOD23	
MV	1SV272	SANYO	pin	V _R >50 B; I _F <100 mA; V _F (I _F =100 mA)<1 B; I _R <0.5 mkA	SOT23,SOD23	A•n.c.•K
ΜV	BS170F	ZETEX	nMOS	V _{DS} =60 B; I _D =150 mA; P _D =330 mB _T	SOT23,SOD23	CO100 53
MX	BS250F	ZETEX	pMOS	V _{DS} =45B; I _D =90 mA; P _D =330 mBT; Q _E =200 mCm; R _{DS(on)} =5 Om	SOT23,SOD23	G·S·D
MY	VN10LF	ZETEX	nMOS	V _{DS} =60 B; I _D =150 мА; Р _D =330 мВт	SOT23,SOD23	G·S·D





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
MZ	ZVN4106F	ZETEX	nMOS	V _{DS} =60 B;I _D =200 мA; P _D =330 мВт; g _F =75 мСм; R _{DS(on)} =25 Ом	S0T23,S0D23	G-S-D
MZT	ADM 1810-10AKS	AD	mrc	V _{TR} =4.35 B; V _{DD} =15.5 B; I _{DC} <16 мкA	SOT323,SC70	V _{CC} •RST•GND
MZT	ADM 1810 - 10ART	AD	mrc	V _{TR} =4.35 B; V _{DD} =15.5 B; I _{DD} <16 MKA	SOT23,SOD23	RST-V _{CC} -GND
MZV	ADM 1810-5AKS	AD	mrc	V _{TR} =4.62 B; V _{TD} =15.5 B; I _{CC} <16 мкА	S0T323,SC70	V _{oc} •RST•GND
MZV	ADM 1810-5ART	AD	mrc	V _{TR} =4.62 B; V _{TD} =15.5 B; I _{TC} <16 MKA	SOT23,SOD23	RST • V _{oc} • GND
N	BAV70	VISH	di×2	V_R <70 B; I_F <300 mA; V_F (I_F = 150 mA)<1.25 B; I_R <5.0 mkA; C_0 <4.0 n Φ ; t_{BR} <6 t_{C}	SOT23,SOD23	A1-A2-K1,K2
N	DAN202K	ROHM	di×2	V _B < 80 B; I _E < 300 mA; P _D < 200 mBT; V _E (I _E = 100 mA) < 1.2 B; t _{BB} < 4 Hc	S0T346,SC59	A1-A2-K1,K2
N	DAN202U	ROHM	di×2	V _B < 80 B; I _E < 300 mA; P _D < 200 mBT; V _E (I _E = 100 mA) < 1.2 B; t _{BB} < 4 HC	S0T323,SC70	A1-A2-K1,K2
N	DAN222	ROHM	di×2	V _B < 80 B; I _E < 300 mA; P _D < 150 mB⊤; V _E (I _E = 100 mA) < 1.2 B; t _{BB} < 4 Hc	S0T416.SC75A	
N	DAN222M	ROHM	di×2	V _B <80 B; I _E <300 mA; P _D <150 mBr; V _E (I _E =100 mA)<1.2 B; t _{BB} <4 hc	VMT3,VMD3	A1+A2+K1,K2
NO	TN0200T	SL	nMOS	V _{DS} =20 B;I _D =730 mA;P _D =350 mBT;I _{DSS} =820 mA;Q _E =4 mCm	SOT23.SOD23	
NO	TN0200T	NS	nMOS	V _{DS} =20 B;I _D =730 mA;P _D =350 mBT;I _{DSS} =820 mA;Q _E =4 mCm	SOT23.SOD23	13000001000
NO1	DDTC113TCA	DIODS	Dnon	V _{CC} =50B;I _C =100 мА;P _D <200 мВт; R11к	SOT23.SOD23	57(107(107)
N01	DDTC113TE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mB⊤; R1 1 κ	SOT523	B-E-C
NO1	DDTC113TKA	DIODS	Dnpn	V _{CC} =50B;I _C =100 mA;P _D <200 mBT; R11 K	SOT346,SC59	0.00
NO1	DDTC113TUA	DIODS	Dnpn	V _{CC} =50B;I _C =100 mA;P _D <200 mBT; R11 K	SOT323,SC70	
NO2	DDTC113ZCA	DIODS	Dnpn	V _{CC} =50B; I _C =100 mA; P _D <200 mBτ; 1 κ/10 κ	SOT23,SOD23	
N02	DDTC113ZE	DIODS	Dnpn	V _{CC} =50B; I _C =100 mA; P _D <200 mB+; 1 k/10 k	SOT523	B·E·C
N02	DDTC113ZKA	DIODS	Dnon		SOT346,SC59	2550227755
NO2		DIODS	C100000	V _{CC} =50B; I _C =100 mA; P _D <200 mB+; 1 k/10 k	EM. 2013 SEC. 2 \$200 SEC.	Land Company Company
	DDTC113ZUA		Dnpn	V _{CC} =50B; I _C =100 mA; P _D <200 mBτ; 1 κ/10 κ	SOT323,SC70	100000000000000000000000000000000000000
N03	DDTC123TCA	DIODS	Dnpn	V _{CC} =50B; I _C =100 mA; P _D <200 mB;; R ₁ 2.2 k	SOT23,SOD23	
N03	DDTC123TE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mB⊤; R ₁ 2.2 κ	SOT523	B·E·C
N03	DDTC123TKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; R ₁ 2.2 κ	SOT346,SC59	
N03	DDTC123TUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D < 200 mB⊤; R ₁ 2.2 κ		B-E-C
N04	DDTC123ECA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 2.2 k/2.2 k	S0T23,S0D23	
N04	DDTC123EE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; 2.2 κ/2.2 κ	SOT523	B.E.C
N04	DDTC123EKA	DIODS	Dnpn	V _{CC} =50 B; I _C = 100 mA; P _D < 200 mB+; 2.2 k/2.2 k	SOT346,SC59	120000 00
N04	DDTC123EUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; 2.2 к/2.2 к	S0T323,SC70	
N05	DDTC123YCA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; 2.2 к/10 к	SOT23,SOD23	
N05	DDTC123YE	DIODS	Dnpn	V _{CC} =50B; I _C =100 mA; P _D <150 mBT; 2.2 к/10 к	SOT523	B·E·C
N05	DDTC123YKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мA; Р _D <200 мВт; 2.2 к/10 к	SOT346,SC59	
N05	DDTC123YUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 2.2 к/10 к	SOT323,SC70	B·E·C
N05	S02484	SGS	npn	V_{CB0} =60 B; I_C =200 mA; P_D =200 mBT; f_T >60 MF I_L	SOT23,SOD23	72277 72
N06	DDTC123JCA	DIODS	Dnpn	V _{CC} =50 B; I _C = 100 mA; P _D < 200 mBT; 2.2 k/47 k	S0T23,S0D23	B·E·C
N06	DDTC123JE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mB t; 2.2 k/47 k	SOT523	B·E·C
N06	DDTC123JKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 2.2 k/47 k	SOT346,SC59	B·E·C
N06	DDTC123JUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 2.2 к/47 к	S0T323,SC70	B·E·C
N07	DDTC143TCA	DIODS	Dnpn	V _{CC} =50 B; I _C = 100 мА; P _D < 200 мВт; R ₁ 4.7 к	SOT23,SOD23	B·E·C
N07	DDTC143TE	DIODS	Dnpn	V _{cc} =50 B; L _c =100 мА; P _C <150 мВт; В; 4.7 к	SOT523	B·E·C
N07	DDTC143TKA	DIODS	Dnpn	V _{cc} =50 B; I _c =100 мА; P ₀ <200 мВт; В; 4.7 к	SOT346,SC59	B·E·C
N07	DDTC143TUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мА; P _D <200 мВт; В; 4.7 к	SOT323,SC70	B·E·C
N08	DDTC143ECA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; 4.7 к/4.7 к	SOT23,SOD23	B·E·C
NO8	DDTC143EE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mB+; 4.7 к/4.7 к	SOT523	B·E·C
N08	DDTC143EKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D < 200 mB t; 4.7 k/4.7 k	SOT346,SC59	
NO8	DDTC143EUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D < 200 mB⊤; 4.7 к/4.7 к	SOT323,SC70	
NO8	S0930	SGS	non	V _{CB0} =45B, I _C =30 мA; P _D =200 мBт; h ₂₁ <600; f _T >200 МΓц	SOT23.SOD23	2232023-99
N09	DDTC123XCA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 4.7 κ/10 κ	SOT23,SOD23	
N09	DDTC123XE	DIODS	Dnon	V _{CC} =50B; I _C =100 mA; P _D <150 mBτ; 4.7 κ/10 κ	SOT523	B·E·C
NO9	DDTC123XEA	DIODS	Dnpn	V _{CC} =50B,I _C =100 MA,P _D <130 MBT, 4.7 K/10 K	SOT346,SC59	
NO9	DDTC123XKA	DIODS	Dnpn		S0T323,SC70	
NU9 N1	MMBF201N	MOT		V _{CC} =50 B; I _C =100 mA; P _D <200 mBτ; 4.7 κ/10 κ V _{DS} =20 B; I _D =200 mA	SOT23,SOD23	

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
N1	MMBT100	FAIR	npn	V _{G80} =75 B; I _C =500 mA; P _D =350 mB1; h ₂₁ =450; f _T >250 MFu	SOT23,SOD23	B·E·C
N1	TN0201T	SIL	nMOS	V _{DS} =20 B; I _D =390 MA; P _D =350 MBT; g _E =450 MCM; R _{DS(np)} =0.75 OM	SOT23,SOD23	G-S-D
N1	TN0201T	TEMIC	nMOS	V _{DS} =20 B; I _D =390 MA; P _D =350 MBT; Q _E =450 MCM; R _{DS(qD)} =0.75 OM	SOT23,SOD23	G·S·D
N10	DDTC143FCA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D < 200 mBT; 4.7 k/22 k	SOT23.SOD23	B-E-C
N10	DDTC143FE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; 4.7 к/22 к	SOT523	B-E-C
N10	DDTC143FKA	DIODS	Dnpn	V _{GG} =50 B; I _G =100 мА; Р ₀ <200 мВт; 4.7 к/22 к	SOT346,SC59	1000010000
N10	DDTC143FUA	DIODS	Dnpn	V _{GG} =50 B; I _G =100 mA; P _D < 200 mBT; 4.7 k/22 k	SOT323,SC70	100000
N10	S0918	SGS	non	V _{GEO} =15B; I _G =30 mA; P _D =200 mBt; f _T >600 MFu,	SOT23,SOD23	
N11	DDTC143ZCA	DIODS	Dnpn	V _{GC} =50 B; I _C =100 mA; P _D <200 mBT; 4.7 k/47 k	SOT23,SOD23	
N11	DDTC143ZE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; 4.7 k/47 k	SOT523	B·E·C
N11	DDTC143ZKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 4.7 k/47 k	SOT346,SC59	
N11	DDTC143ZUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 4.7 k/47 k	SOT323,SC70	
N11	SO2369	SGS		V _{CR0} =40 B; I _C =200 mA; P _D =200 mBτ; h ₂₁ =40120; f _T >400 MΓц	SOT23,SOD23	160.5377.007
N12		222	npn	050		
	DDTC114TCA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P ₀ <200 mBt; R1 10 k	SOT23,SOD23	
N12	DDTC114TE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; R1 10 k	SOT523	B·E·C
N12	DDTC114TKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBt; R1 10 k	SOT346,SC59	
N12	DDTC114TUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; R1 10 k	SOT323,SC70	
N12	SO2221	SGS	npn	V_{CB0} =60 B; I_C =800 mA; P_D =310 mBT; h_{21} =40120; f_T >250 MFU	SOT23,SOD23	100/1014/12/4
N12	TMPT2221	ALLEG	npn	V _{CB0} =60 B; I _{CB0} < 10 HA; h ₂₁ =40120; V _{CE(sat)} < 0.4 B; f _T >250 MFu	SOT23,SOD23	1107 12 130
N13	DDTC114ECA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мА; Р ₀ <200 мВт; 10 к/10 к	SOT23,SOD23	130000 30
N13	DDTC114EE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мА; P _D <150 мВт; 10 к/10 к	SOT523	B·E·C
N13	DDTC114EKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 10 к/10 к	SOT346,SC59	B-E-C
N13	DDTC114EUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 10 к/10 к	SOT323,SC70	B·E·C
N13	SO2222	SGS	npn	V_{CB0} =60 B; I_C =800 MA; P_D =310 MBT; h_{21} =100300; f_T >250 M Γ_U	SOT23,SOD23	B·E·C
N14	DDTC114YCA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 10 k/47 k	SOT23,SOD23	B-E-C
N14	DDTC114YE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мА; Р _В <150 мВт; 10 к/47 к	SOT523	B-E-C
N14	DDTC114YKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мА; Р _В <200 мВт; 10 к/47 к	SOT346,SC59	B·E·C
N14	DDTC114YUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D < 200 mB⊤; 10 к/47 к	SOT323,SC70	B·E·C
N15	DDTC114WCA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 10 k/4.7 k	SOT23,SOD23	B·E·C
N15	DDTC114WE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мА; P _D <150 мВт; 10 к/4.7 к	SOT523	B-E-C
N15	DDTC114WKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мА; Р ₀ <200 мВт; 10 к/4.7 к	SOT346,SC59	B·E·C
N15	DDTC114WUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D < 200 mBT; 10 κ/4.7 κ	SOT323,SC70	B·E·C
N16	DDTC124TCA	DIODS	Dnpn	V _{GC} =50 B; I _C =100 mA; P _D <200 mBT; R ₁ 22 K	SOT23.SOD23	B·E·C
N16	DDTC124TE	DIODS	Dnon	V _{CC} =50 B; I _C =100 mA; P _D < 150 mBT; R ₁ 22 k	SOT523	B·E·C
N16	DDTC124TKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D < 200 mBT; R ₁ 22 k	SOT346.SC59	B·E·C
N16	DDTC124TUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мA; P _D <200 мBт; R ₁ 22 к	SOT323.SC70	
N17	DDTC124ECA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мA; P _D <200 мB⊤; 22 к/22 к	SOT23,SOD23	Salara Cara
N17	DDTC124EE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мА; P _D <150 мВт; 22 к/22 к	SOT523	B·E·C
N17	DDTC124EKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mB;; 22 κ/22 κ	SOT346,SC59	CACCO-00000
N17	DDTC124EUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; 22 k/22 k		B·E·C
N18	DDTC124XCA	DIODS	Dnpn	V _{GC} =50 B; I _C =100 mA; P _D <200 mBT; 22 k/47 k	SOT23,SOD23	
N18	DDTC124XE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; 22 k/47 k	S0T523	B·E·C
N18	DDTC124XKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 22 k/47 k	SOT346.SC59	
N18	DDTC124XIVA	DIODS	Dnpn		SOT323,SC70	
N18	S01711	SGS	-0.00	V _{CC} =50 B; I _C =100 mA; P _D <200 mB+; 22 k/47 k	SOT23,SOD23	
	0.0000000000000000000000000000000000000		npn	V _{CB0} =75 B; I _C =800 мА; P _D =310 мВт; h ₂₁ >35; f _T >70 МГц		W000 40
N19	DDTC144TCA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mB _T ; R ₁ 47 κ	SOT23,SOD23	100000000000000000000000000000000000000
N19	DDTC144TE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mBτ; R ₁ 47 κ	SOT523	B·E·C
N19	DDTC144TKA	DIODS	Dnpn	V _{GG} =50 B; I _G =100 mA; P _G <200 mBT; R ₁ 47 κ	SOT346,SC59	
N19	DDTC144TUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мA; P _D <200 мВт; R ₁ 47 к	SOT323,SC70	
N2	BFS520	PHIL	npn	V _{GB0} =20 B; I _C =70 мА; Р ₀ =300 мВт; h ₂₁ =60200; f ₁ =9ГГц	SOT323,SC70	
N2	MGSF1N02LT1	ON		V _{DS} =20B;I _D =750 мA;P _D =400 мВт;R _{DS(on)} <0.13 Ом	SOT23,SOD23	100000000000000000000000000000000000000
N2	MMBC1653N2	MOT	npn	V _{CB0} =150 B; I _C =50 мА; P _D =300 мВт; h ₂₁ =50130	SOT23,SOD23	B-E-C





Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3
N20	DDTC144ECA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мA; P _D <200 мВт; 47 к/47 к	SOT23,SOD23	B·E·C
V20	DDTC144EE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мА; Р _О < 150 мВт; 47 к/47 к	SOT523	B·E·C
V20	DDTC144EKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D < 200 mB ±; 47 κ/47 κ	SOT346,SC59	B·E·C
V20	DDTC144EUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D < 200 mB t; 47 κ/47 κ	SOT323,SC70	B·E·C
N20	S02222A	SGS	non	V _{CBD} =75B; I _C =800 мА; P _D =310 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	B·E·C
N21	DDTC144VCA	DIODS	Dnpn	V _{cc} =50 B; I _c =100 мА; Р _о <200 мВт; 47 к/10 к	SOT23,SOD23	B·E·C
N21	DDTC144VE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мA; P _D <150 мВт; 47 к/10 к	SOT523	B·E·C
N21	DDTC144VKA	DIODS	Dnon	V _{CC} =50 B; I _C =100 мA; P _D <200 мВт; 47 к/10 к	SOT346,SC59	
V21	DDTC144VUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мА; P _D <200 мВт; 47 к/10 к	S0T323,SC70	
N22	DDTC144WCA	DIODS	Dnon	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 47 к/22 к	SOT23.SOD23	
N22	DDTC144WE	DIODS	Dnpn	V _{CC} =50B; I _C =100 mA; P _D <150 mBT; 47 k/22 k	SOT523	B-E-C
V22	DDTC144WKA	DIODS	Dnon	V _{CC} =50B; I _C =100 mA; P _D <200 mBT; 47 κ/22 κ	SOT346.SC59	
V22	DDTC144WUA	DIODS	Dnpn	V _{CC} =50B; l _C =100 mA; P _D < 200 mB; , 47 k/22 k	SOT323.SC70	22000000000
V23	DDTC144WGA	DIODS	Dnon	V _{CC} =50B; l _C =100 mA; P _D <200 mB;; 41 t/22 k	SOT23.SOD23	2000
V23	DDTC115TE	DIODS	1		S0T523	B-E-C
N23		_	Dnpn	V _{CC} =50B; I _C =100 mA; P _D <150 mBT; R ₁ 100 k		
	DDTC115TKA	DIODS	Dnpn	V _{CC} =50B; I _C =100 mA; P _D <200 mB _T ; R ₁ 100 K	SOT346,SC59	
N23	DDTC115TUA	DIODS	Dnpn	V _{CC} =50B; I _C =100 mA; P _D <200 mB _T ; R ₁ 100 K	S0T323,SC70	
N24	DDTC115ECA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 мА; Р _О <200 мВт; 100 к/100 к	SOT23,SOD23	
N24	DDTC115EE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; 100 κ/100 κ	S0T523	B•E•C
N24	DDTC115EKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBτ; 100 κ/100 κ	SOT346,SC59	
N24	DDTC115EUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mB+; 100 κ/100 κ	SOT323,SC70	
V25	DDTC125TCA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; R ₁ 200 k	SOT23,SOD23	
V25	DDTC125TE	DIODS	Dnpn	V_{CC} =50 B; I_{C} =100 mA; P_{D} <150 mBT; R_{1} 200 k	SOT523	B-E-C
N25	DDTC125TKA	DIODS	Dnpn	V_{CC} =50 B; I_{C} = 100 mA; P_{D} < 200 mBT; R_{1} 200 K	SOT346,SC59	B·E·C
N25	DDTC125TUA	DIODS	Dnpn	V_{CC} =50 B; I_C =100 mA; P_D <200 mB t; R_1 200 k	SOT323,SC70	B·E·C
V26	DDTC114GCA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; R2 10 K	SOT23,SOD23	B-E-C
N26	DDTC114GE	DIODS	Dnpn	V _{CC} =50 B; I _C = 100 мA; P _D < 150 мВт; R2 10 к	SOT523	B·E·C
N26	DDTC114GKA	DIODS	Dnpn	V _{CC} =50B; I _C =100 mA; P _D <200 mB t; R2 10 k	SOT346,SC59	B·E·C
N26	DDTC114GUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; R2 10 K	SOT323,SC70	B·E·C
N27	DDTC124GCA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; R ₂ 22 к	SOT23,SOD23	B-E-C
N27	DDTC124GE	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _C <150 mB⊤; R ₂ 22 k	SOT523	B·E·C
N27	DDTC124GKA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mB t; R ₂ 22 κ	SOT346,SC59	B·E·C
N27	DDTC124GUA	DIODS	Dnpn	V _{CC} =50 B; I _C =100 mA; P _D <150 mB ⊤; R ₂ 22 κ	SOT323,SC70	
N27	SO1893	SGS	non	V _{CBO} = 120 B; I _C = 800 мА; P _D =310 мВт; h ₂₁ =40120; f _T >50 МГц	SOT23,SOD23	
N28	DDTC144GCA	DIODS	Dnpn	V _{DC} =50 B; I _C =100 мA; P _D <200 мВт; R ₂ 47 к	SOT23,SOD23	
V28	DDTC144GE	DIODS	Dnon	V _{CC} =50B;I _C =100 мА;Р _D <150 мВт; R ₂ 47 к	SOT523	B·E·C
V28	DDTC144GKA	DIODS	Dnon	V _{CC} =50B; I _C =100 мА; Р _D <200 мВт; R ₂ 47 к	SOT346.SC59	
V28	DDTC144GUA	DIODS	Dnpn	V _{CC} =50B;I _C =100 мA;P _D <200 мВт; R ₂ 47 к	S0T323.SC70	
V28	S03572	SGS	non	V _{CB0} =15B; P _D =200 mBr; f _T >1ΓΓц	SOT23,SOD23	2000000000
V29	DDTC115GCA	DIODS	Dnon	V _{CC} =50 B; l _C =100 mA; P _D < 200 mBT; R ₂ 100 K	SOT23,SOD23	
V29	DDTC115GE	DIODS	Dnon	V _{CC} =50B; I _C =100 mA; P _D <150 mB; F _B =100 k	SOT523	B·E·C
N29 N29	DDTC115GKA	DIODS	Dnon	V _{CC} =50 B; I _C =100 MA; P _D <100 MBT; R _C 100 K	S0T346,SC59	
N29 N29	DDTC115GIA	DIODS	Dnpn		S0T323,SC70	
N29 N29	KDV152S	KEC	bd	V _{CC} =50 B; I _C =100 mA; P _D < 200 mB;; R _C =100 k	SOT23,SOD23	
	D-50-00-00-00-00-00-00-00-00-00-00-00-00-			V _R =15B; I _R =50 μA; C2 B=45 πΦ; C _{8 B} =26 πΦ; R _S <0.3 OM		100000000000000000000000000000000000000
N3	MGSF1N03LT1	ON	nMOS	V _{DS} =30B; I _D =1.5A; P _D =420 MBT; R _{DS(on)} < 0.145 0 M	SOT23,SOD23	
N3	MMBC1653N3	MOT	npn	V _{CB0} *150 B; I _C *50 MA; P ₀ *300 MBT; h ₂₁ *100220	SOT23,SOD23	
N4	MMBC1653N4	MOT	npn	V _{CB0} =150 B;I _C =50 MA;P ₀ =300 MBT;h ₂₁ =150330	SOT23,SOD23	
V44	S03571	SGS	npn	V _{CBO} =15B; P _O =200 мВт; f ₇ >1.2 ГГц	SOT23,SOD23	
V47	S03570	SGS	npn	V _{CBO} = 15B; P _D =200 мВт; f _T > 1.5 ГГц	SOT23,SOD23	200000000000000000000000000000000000000
√5	MMBC1654N5	MOT	npn	V _{CB0} = 180 B; I _C = 50 мА; Р ₀ = 300 мВт; h ₂₁ = 50130	SOT23,SOD23	
N54	S02221A	SGS	npn	V_{CB0} =75B; I_C =800 mA; P_D =310 mBr; h_{21} =40120; f_T >250 MF μ	SOT23,SOD23	12120000
V54	TMPT2221A	ALLEG	non	V _{CB0} =75B; I _{CB0} <10 HA; h ₂₁ =40120; V _{CEIsati} <0.3 B; f _T >250 MFu	SOT23,SOD23	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
N6	BFS25A	PHIL	npn	I _C =6.5 мА; Р _D =32 мВт; h ₂₁ > 40; f _T =5.5 ГГц	SOT323,SC70	B-E-C
N6	MMBC1654N6	MOT	npn	V _{CB0} =180 B; I _C =50 мА; P _D =300 мВт; h ₂₁ =100220	SOT23,SOD23	B-E-C
N7	MMBC1654N7	MOT	npn	V _{CR0} =180 B; I _C =50 mA; P _D =300 mBr; h ₂₁ =150330	SOT23,SOD23	B·E·C
N71	SO3904	SGS	non	V _{сэп} =60 B; I _C =200 мА; P _D =300 мВт; h ₂₁ =100300; f _T >300 МГц	SOT23,SOD23	B-E-C
N72	SO3903	SGS	npn	V _{сво} =60 B; I _C =200 мА; P _D =300 мВт; h ₂₁ =50150; f _T >250 МГц	SOT23,SOD23	B-E-C
N79	SO5550	SGS	npn	V_{CB0} =160 B; I_C =600 mA; P_D =200 mBT; h_{21} =60250; f_T >100 MF $_{II}$	SOT23.SOD23	B-E-C
N80	SO5551	SGS	npn	V _{DB0} =180 B; I _D =600 мА; P _D =200 мВт; h ₂₁ =80250; f _T >100 МГц	SOT23,SOD23	B-E-C
N81	SO2369A	SGS	npn	V _{CR0} =40 B; I _C =200 mA; P _D =200 mBT; h ₂₁ =40120; f _T >500 MFu	SOT23,SOD23	
N9	1SS372	TOSH	shd×2	V _B < 10 B; I _E < 100 mA; V _E (I _E = 100 mA) < 0.5 B; C _D < 40 mΦ	S0T323,SC70	
N9	1SS374	TOSH	shd×2	V _B >10 B; V _E (I _E =100 mA) < 0.5 B; I _E (V _B =10 B) < 20 mrA; C _T < 40 mΦ	SOT346.SC59	
N9	DAN222	ON	di×2	V _B <80 B; I _E <300 mA; P _D <150 mBr; V _E (I _E =100 mA)<1.2 B; t _{BB} <4 hc	SOT416,SC75A	
N91	S0642	SGS	npn	V _{свя} =300 B; I _с =100 мА; P _п =310 мВт; h ₂₁ >40; f _T >50 МГц	SOT23,SOD23	
N94	S0517	SGS	dpnp	V _{CR0} =40 B; I _C =400 MA; P _D =350 MB; h ₂₁ >30000; f _T >220 MFu	SOT23,SOD23	120,537,007
NA	FMMTA05R	ZETEX	non	V _{CRO} =60 B; I _C =500 mA; P _D =330 mBT; h ₂₁ >50; f _T >100 MFu	SOT23,SOD23	350.74
NA NA	KRC401	KEC	non	V _{GR0} =50 B; I _G =100 mA; P _G =100 mBT; R ₁ /R ₀ =4.7/4.7 KOM	SOT323.SC70	20-21-00
NA NA	RN1443A	TOSH	Dnpn	V _{CR0} =50 B; I _C =300 mA; P _D =200 mBt; h ₂₁ =200700; f _T =30 MFu; R ₁ =22 kOm	SOT346,SC59	
NA1	MMBT100A	FAIR	npn	V _{CR0} =75 B; I _C =500 MA; P _D =250 MB; h ₂₁ =260740; f _T =35 MFц	SOT23,SOD23	
NB	BF599	SIEM	npn	V _{CR0} =40 B; I _C =25 мA; Р _D =280 мВт; h ₂₁ >38; f _T =550 МГц	SOT23,SOD23	100000000000000000000000000000000000000
NB	DAP222U	ON	di×2	V _B <80 B; I _F <300 mA; P _D <150 mB _T ; V _F (I _F =100 mA)<1.2 B; t _{BB} <4 hc	SOT323,SC70	TOTAL Z
NB NB	FMMTA55R	ZETEX	ono		SOT23.SOD23	100000000000000000000000000000000000000
NB	KRC402	KEC	1 1	V _{CBD} =60 B; I _C =500 мА; P _D =330 мВт; h ₂₁ >50; f _T >100 МГц	SOT323,SC70	22.22
0 3			npn	V _{CBO} =50 B; I _C =100 mA; P _O =100 mBr; R ₁ /R ₂ =10/10 xOm		
NB	RN1443B	TOSH	Dnpn	V _{GB0} =50 B; I _C =300 mA; P _D =200 mBr; h ₂₁ =3501200; f _T =30 MFu; R ₁ =22 κOm	SOT346,SC59	
NC	BF840	CDIL	npn	V _{CB0} =40 B; I _C =25 mA; P _D =280 mBT; h ₂₁ =65220; f _T >380 MFц	SOT23,SOD23	
NC	BF840	SIEM	npn	V _{CB0} =40 B; I _C =25 мA; P ₀ =280 мВт; h ₂₁ =65220; f ₇ =380 МГц	SOT23,SOD23	100000000000000000000000000000000000000
NC	KRC403	KEC	npn	V _{GB0} =50 B; I _G =100 mA; P _D =100 mBt; R ₁ /R ₂ =22/22 kOm	SOT323,SC70	100000000000000000000000000000000000000
NCp	BF840	PHIL	npn	V _{CB0} =40 B; I _C =25 мА; Р ₀ =250 мВт; I _B =4.515 мкА; f _T =380 МГц	SOT23,SOD23	100000
ND	2SD1306D	REN	npn	V _{CB0} =30 B; I _C =700 mA; P _D =150 mBt; h ₂₁ =250500	SOT23,SOD23	
ND	BF841	CDIL	npn	V_{CB0} =40 B; I_C =25 mA; P_D =280 mBr; h_{21} =35125; f_T >380 MFu	SOT23,SOD23	
ND	BF841	SIEM	npn	V_{CB0} =40 B; I_C =25 mA; P_0 =280 mBr; h_{21} =35125; f_T =380 MF μ	SOT23,SOD23	2000
ND	KRC404	KEC	npn	V_{CB0} =50 B; I_C =100 mA; P_D =100 mBT; R_1/R_2 =47/47 KOM	SOT323,SC70	100000000
NDp	BF841	PHIL	npn	V _{CB0} =40 B; I _C =25 мA; P ₀ =250 мВт; I _B =828 мкА; f ₁ =380 МГц	SOT23,SOD23	1000000000
NE	2SD1306E	REN	npn	V_{CB0} =30 B; I_C =700 mA; P_D =150 mBt; h_{21} =400800	SOT23,SOD23	1000000 000
NE	KRC405	KEC	npn	V _{CB0} =50 B; I _C =100 мA; P _D =100 мВт; R ₁ /R ₂ =2.2/47 кОм	SOT323,SC70	B-E-C
NF	KRC406	KEC	npn	V_{GB0} =50 B; I_C =100 mA; P_D =100 mBt; R_1/R_2 =4.7/47 кOm	SOT323,SC70	B-E-C
NK	KRC410	KEC	npn	V _{CB0} = 50 B; I _C = 100 мА; P _D = 100 мВт; R ₁ = 4.7 кОм	SOT323,SC70	B-E-C
NM	KRC411	KEC	npn	V _{CB0} =50 B; I _C =100 mA; P _D =100 mBt; R ₁ =10 kOm	SOT323,SC70	B-E-C
NN	KRC412	KEC	npn	V _{CB0} =50 B; I _C =100 mA; P _D =100 mBt; R ₁ =100 kOm	SOT323,SC70	B-E-C
NO	KRC413	KEC	npn	V _{CB0} =50 B; I _C = 100 mA; P _D =100 mBt; R ₁ =22 kOm	SOT323,SC70	B-E-C
NP	KRC414	KEC	npn	V _{CB0} =50 B; I _C =100 мA; P _D =100 мВт; R ₁ =47 кОм	SOT323,SC70	B-E-C
NS	TN0200TS	SIL	nMOS	V _{DS} =20 B; I _D =1200 mA; P _D =1000 mBT; g _F =2200 mCm; R _{DS/onl} =0.4 Om	SOT23,SOD23	G-S-D
005	S02484R	SGS	npn	V _{CB0} =60 B; I _C =200 мА; P _D =200 мВт; f _T >60 МГц	SOT23,SOD23	E-B-C
008	S0930R	SGS	npn	V _{CB0} =45 B; I _C =30 мA; P _D =200 мВт; h ₂₁ <600; f _T >200 МГц	SOT23,SOD23	E·B·C
010	S0918R	SGS	non	V _{CF0} =15B;I _C =30 мA;P _D =200 мВт;f _T >600 МГц	SOT23,SOD23	E-B-C
012	S02221R	SGS	npn	V _{GB0} =60 B; I _G =800 мА; P _D =310 мВт; h ₂₁ =40120; f _T >250 МГц	SOT23,SOD23	E·B·C
013	SO2222R	SGS	npn	V _{CB0} =60 B; I _C =800 мА; P _D =310 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	-
020	S02222AR	SGS	npn	V _{CP0} =75 B; I _C =800 мA; P ₀ =310 мBт; h ₂₁ =100300; f ₁ >250 МГц	SOT23,SOD23	E·B·C
027	SO1893R	SGS	non	V _{DB0} =120 B; I _D =800 мА; P _D =310 мВт; h ₂₁ =40120; f _T >50 МГц	SOT23,SOD23	100000000000000000000000000000000000000
054	S02221AR	SGS	npn	V _{СВО} =75 B; I _C =800 мА; P _D =310 мВт; h ₂₁ =40120; f _T >250 МГц	SOT23,SOD23	
079	S05550R	SGS	npn	V _{GB0} =160 B; I _G =600 MA; P _G =200 MBT; h ₂₁ =60250; f _T >100 MFq	SOT23,SOD23	
080	S05551R	SGS	npn	V _{CB0} =180 B; I _C =600 MA; P _D =200 MBT; h ₂₁ =80250; f _T >100 MFu	SOT23,SOD23	
000	1SS377	TOSH	shd×2	V _B >10 B; V _E (I _E =100 MA) < 0.5 B; I _E (V _B =10 B) < 20 MKA; C _T <40 MΦ	SOT346.SC59	
09	1SS378	TOSH	shd~2	V _R <10 B; I _F <100 mA; V _F (I _F =100 mA)<0.5 B; C _R <20 πΦ	SOT323,SC70	





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
09	1SS379	TOSH	di×2	V _B < 80 B; I _E < 100 mA; V _E (I _E = 100 mA) < 1.3 B; I _B < 0.01 m kA	SOT346,SC59	A1-K2-K1,A2
09	1SS385	TOSH	shd×2	V _B <10B; V _C (I _E =100 mA)<0.5B; I _B (V _B =10B)<20 mκA; C _T <20 nΦ	SOT416,SC75A	A1-A2-K1,K2
09	1SS385F	TOSH	shd×2	$V_B < 10B$; $V_B(I_F = 100 \text{ mA}) < 0.5B$; $I_B(V_B = 10B) < 20 \text{ m/A}$; $C_T < 20 \text{ n}\Phi$	SOT490,SC89	A1 • A2 • K1, K2
091	S0642R	SGS	non	V _{сво} =300 B; I _с =100 мA; P _о =310 мВт; h ₂₁ >40; f _T >50 МГц	SOT23,SOD23	E-B-C
Р	BAW56	VISH	di×2	$V_{\rm R}\!<\!70B_{\rm i}I_{\rm F}\!<\!300{\rm mA;}V_{\rm F}\!(I_{\rm F}\!=\!150{\rm mA})\!<\!1.25B_{\rm i}I_{\rm R}\!<\!5.0{\rm mkA;}C_0\!<\!4.0{\rm n\Phi;}t_{\rm BR}\!<\!6{\rm Hz}$	S0T23,S0D23	K1-K2-A1,A2
Р	DAP202K	ROHM	di×2	V _R <80 B; I _F <300 mA; P _D <200 mBr; V _F (I _F =100 mA)<1.2 B; t _{PR} <4 nc	SOT346,SC59	K1 · K2 · A1,A2
Р	DAP202U	ROHM	di×2	V _R <80 B; I _F <300 mA; P _D <200 mBT; V _F (I _F =100 mA)<1.2 B; t _{RR} <4 hc	SOT323,SC70	K1 · K2 · A1,A2
Р	DAP222	ROHM	di×2	V _R <80 B; I _F <300 mA; P _D <150 mBT; V _F (I _F =100 mA)<1.2 B; t _{RR} <4 hc	SOT416,SC75A	K1 · K2 · A1,A2
Р	DAP222M	ROHM	di×2	V_R <80 B; I_F <300 mA; P_D <150 mBT; V_F (I_F =100 mA)<1.2 B; t_{RR} <4 hc	VMT3,VMD3	K1 · K2 · A1,A2
P0	HSMS2850	HP	shd	V _E (I _F =1 мA) < 0.25 B; C _T =0.3 пΦ	SOT23,SOD23	A·n.c.•K
P0	HSMS285B	HP	shd	V _E (I _F =1 мA) < 0.25 B; C _T =0.3 пΦ	SOT323,SC70	A+n.c.+K
P0	TP0101T	SIL	pMOS	V _{DS} =20 B;I _D =600 мA; P _D =350 мВт; g _F =1300мСм; R _{DS(on)} =0.65 Ом	SOT23,SOD23	G·S·D
P0	TP0101T	TEMIC	pMOS	V _{DS} =20 B;I _D =600 мA; P _D =350 мВт; g _E =1300мСм; R _{DS(m)} =0.65 Ом	SOT23,SOD23	G·S·D
P01	DDTA113TCA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мА; P _D <200 мВт; R ₁ 1 к	SOT23,SOD23	B·E·C
P01	DDTA113TE	DIODS	Dpnp	V _{CC} =50 B; I _C =100 nA; P _D <150 nBT; R ₁ 1 κ	SOT523	B·E·C
P01	DDTA113TKA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; R ₁ 1 K	SOT346,SC59	B-E-C
P01	DDTA113TUA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мА; P _D <200 мВт; R ₁ 1 к	SOT323,SC70	B·E·C
p01	PDTA143ET	PHIL	Dpnp	V _{CB0} =50 B; I _C =100 mA; P _D =250 mBr; h ₂₁ >30; 4.7 kOm/4.7 kOm	SOT23,SOD23	B·E·C
p01	PDTA143EU	PHIL	Dpnp	V_{CB0} =50B; I_C =100 mA; P_D =250 mBT; h_{21} >30; 4.7 kOm/4.7 kOm	SOT323,SC70	B·E·C
P01	SO2906	SGS	pnp	V_{CB0} =40B; I_C =150 mA; P_D =300 mBT; h_{21} =40120; f_T >200 MF $_{II}$	SOT23,SOD23	B·E·C
P02	DDTA113ZCA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 1 к/10 к	SOT23,SOD23	B-E-C
P02	DDTA113ZE	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; 1 к/10 к	SOT523	B-E-C
P02	DDTA113ZKA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мA; P _D < 200 мВт; 1 к/10 к	SOT346,SC59	B·E·C
P02	DDTA113ZUA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 1 к/10 к	SOT323,SC70	B·E·C
p02	PDTC143ET	PHIL	Dnpn	V _{CB0} =50B; I _C =100 mA; P _D =250 mBt; h ₂₁ >30; 4.7 kOm/4.7 kOm	SOT23,SOD23	B·E·C
p02	PDTC143EU	PHIL	Dnpn	V _{CB0} =50B; I _C =100 mA; P _D =250 mBt; h ₂₁ >30; 4.7 kOm/4.7 kOm	SOT323,SC70	B·E·C
P03	DDTA123TCA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; R12.2 k	SOT23,SOD23	B·E·C
P03	DDTA123TE	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; R12.2 k	SOT523	B·E·C
P03	DDTA123TKA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; R12.2 k	SOT346,SC59	B-E-C
P03	DDTA123TUA	DIODS	Dpnip	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; R12.2 k	SOT323,SC70	B·E·C
p03	PDTA114ET	PHIL	Donio	V _{CB0} =50B; I _C =100 мA; P _D =200 мВт; h ₂₁ >30; 10 кОм/10 кОм	SOT23,SOD23	B·E·C
P03	SO2907A	SGS	pnp	V_{CB0} =60 B; I_C =200 mA; P_D =300 mBr; h_{21} =100300; f_T >200 MFu	SOT23,SOD23	B-E-C
P04	DDTA123ECA	DIODS	Donio	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 2.2 k/2.2 k	SOT23,SOD23	B·E·C
P04	DDTA123EE	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; 2.2 k/2.2 k	SOT523	B-E-C
P04	DDTA123EKA	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D < 200 mB+; 2.2 k/2.2 k	SOT346,SC59	B·E·C
P04	DDTA123EUA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D < 200 mB+; 2.2 k/2.2 k	SOT323,SC70	
p04	PMSS3904	PHIL	non	V _{CB0} =60 B; I _C =200 mA; P _D =300 mBr; h ₂₁ =100300; f _T >180 MFu	SOT23,SOD23	
P05	DDTA123YCA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мA; P _D <200 мВт; 2.2к/10к	SOT23,SOD23	STREET, STREET
P05	DDTA123YE	DIODS	Dono	V _{CC} =50B; I _C =100 mA; P _D <150 mB+; 2.2 к/10 к	SOT523	B·E·C
P05	DDTA123YKA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 2.2 k/10 k	SOT346,SC59	B·E·C
P05	DDTA123YUA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 2.2 k/10 k	S0T323,SC70	10.00
p05	PDTA124ET	PHIL	Dpnp	V _{CB0} =50B; I _C =30 MA; P _D =250 MBT; h ₂₁ >56	SOT23,SOD23	B·E·C
005	PDTA124ET	PHIL	Donio	V _{CB0} =50 B; I _C =100 mA; P _D =250 mBr; h ₂₁ >60; 22 kOm/22 kOm	SOT23,SOD23	B·E·C
005	PDTA124EU	PHIL	Donio	V _{CR0} =50B; I _C =100 mA; P _D =250 mBt; h ₂₁ >60; 22 kOm/22 kOm	SOT323,SC70	
P05	S02907	SGS	onp	V _{CBO} =40 B; I _C =200 мА; P _D =300 мВт; h ₂₁ =100300; f _T >200 МГц	SOT23,SOD23	030,000,000
P06	DDTA123JCA	DIODS	Dono	V _{CC} =50B; I _C =100 mA; P _D <200 mB t; 2.2 k/47 k	SOT23.SOD23	222000000
P06	DDTA123JE	DIODS	Dono	V _{CC} =50B; I _C =100 mA; P _D <150 mB+; 2.2 k/47 k	SOT523	B-E-C
P06	DDTA123JKA	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <200 mB t; 2.2 k/47 k	SOT346,SC59	-
P06	DDTA123JUA	DIODS	Dono	V _{CC} ⁻ 50B; I _C ⁻ 100 mA; P _D <200 mB _T ; 2.2 k/47 k	SOT323.SC70	
006	PDTC124EU	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 mA; P _D =250 mBT; h ₂₁ >60; 22 kOm/22 kOm	S0T323,SC70	
	PMSS3906	PHIL	pnp	V _{CB0} =40 B; I _C =200 мА; P _D =200 мВт; h ₂₁ =100300; f _T >150 МГц	SOT23.SOD23	

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
p06	PMSS3906	PHIL	gng	V _{сво} =40 B; I _c =200 мА; P _D =200 мВт; h ₂₁ =100300; f _T >150 МГц	SOT323,SC70	B-E-C
P06	SO2894	SGS	pnp	V _{CB0} =12 B; I _C =200 мA; P _D =300 мВт; h ₂₁ =40150; f _T >400 МГц	SOT23.SOD23	B-E-C
P07	DDTA143TCA	DIODS	Dono	V _{cc} =50 B; I _c =100 мA; P _n <200 мВт; R14.7 к	SOT23.SOD23	
P07	DDTA143TE	DIODS	Dono	V _{CC} =50 B; I _C =100 мА; Р _D <150 мВт; R14.7 к	SOT523	B-E-C
P07	DDTA143TKA	DIODS	Dono	V _{CC} =50 B; I _C =100 мА; P _D <200 мВт; R14.7 к	SOT346,SC59	
P07	DDTA143TUA	DIODS	Dono	V _{DC} =50 B; I _C =100 мА; P _D <200 мВт; R14.7 к	SOT323.SC70	1000010000
p07	PDTA144ET	PHIL	Donp	V _{CB0} =50 B; I _C =100 mA; P _D =250 mBr; h ₂₁ >80; 47 kOm/47 kOm	SOT23,SOD23	7007
p07	PDTA144EU	PHIL	Dono	V _{CR0} =50 B; I _C =100 MA; P _D =250 MBT; h ₂₁ >80; 47 KOM/47 KOM	SOT323,SC70	
P08	DDTA143ECA	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <200 mB;; 127 × 63 m/4 × 63	SOT23,SOD23	
P08	DDTA143EE	DIODS	Donp	V _{CC} =50 B; I _C =100 MA; P _D <150 MBT; 4.7 K/4.7 K	SOT523	B·E·C
P08	DDTA143EKA	DIODS	Donp	V _{CC} =50 B; I _C =100 MA; P _D < 200 MBT; 4.7 K/4.7 K	SOT346,SC59	
P08	DDTA143EUA	DIODS	Dono		SOT323,SC70	177011000000
	2,000,000,000,000	PHIL		V _{CC} =50 B; I _C =100 mA; P _D <200 mBr; 4.7 κ/4.7 κ		100000000000000000000000000000000000000
p08	PDTC144ET	00000	Dnpn	V _{CB0} =50 B; I _C =100 mA; P ₀ =250 mB _T ; h ₂₁ >80; 47 κOm/47 κOm	SOT23,SOD23	100000000000000000000000000000000000000
p08	PDTC144EU	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 mA; P _D =250 mBr; h ₂₁ >80; 47 kOm/47 kOm	SOT323,SC70	200
P09	DDTA123XCA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мА; P _D <200 мВт; 4.7 к/10 к	SOT23,SOD23	
P09	DDTA123XE	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мA; P _D <150 мBт; 4.7 κ/10 к	SOT523	B-E-C
P09	DDTA123XKA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мA; P _D <200 мВт; 4.7 к/10 к	SOT346,SC59	
P09	DDTA123XUA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мA; P _D <200 мВт; 4.7 к/10 к	SOT323,SC70	T000T0070
p09	PDTB114ET	PHIL	Dnpn	V _{CB0} =50 B; I _C =500 мА; P _D =250 мВт; h ₂₁ >56; 10 кОм/10 кОм	SOT23,SOD23	2000 00
p09	PDTC114EU	PHIL	Dnpn	V _{CB0} =50 B; I _C =50 мA; P ₀ =250 мВт; h ₂₁ >30; 10 кОм/10 кОм	SOT323,SC70	130000 20
P1	BFR92	PHIL	npn	V _{CB0} =20 B; I _C =25 мА; P ₀ =273 мВт; h ₂₁ >40; f _T =4500 МГц	SOT23,SOD23	B-E-C
P1	BZX84C11T	DIODS	dz	V _Z (I _{ZT} =5mA)=10.411.6B; Z _{ZT} (I _{ZT} =5mA) < 20 Om	SOT523	A·n.c.·K
P1	SST201	SIL	nFET	V _{DS} =30 B; P _D =350 мВт; I _{DSS} =20 135 мА; R _{DS(cn)} <85 Ом	SOT23,SOD23	D·S·G
P10	DDTA143FCA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; 4.7 к/422 к	SOT23,SOD23	B-E-C
P10	DDTA143FE	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <150 mB⊤; 4.7 к/422 к	SOT523	B-E-C
P10	DDTA143FKA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 4.7 κ/422 κ	SOT346,SC59	B-E-C
P10	DDTA143FUA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мА; Р _D < 200 мВт; 4.7 к/422 к	SOT323,SC70	B-E-C
p10	PDTD114ET	PHIL	Dnpn	V _{CB0} =50 B; I _C =500 mA; P _D =250 mBт; h ₂₁ > 56; 10 kOm/10 kOm	SOT23,SOD23	B·E·C
P11	DDTA143ZCA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 4.7 κ/47 κ	SOT23,SOD23	B·E·C
P11	DDTA143ZE	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; 4.7 κ/47 κ	SOT523	B-E-C
P11	DDTA143ZKA	DIODS	Dpnp	V _{cc} =50 B; I _c =100 мА; Р _п <200 мВт; 4.7 к/47 к	SOT346,SC59	B·E·C
P11	DDTA143ZUA	DIODS	Dono	V _{cc} =50 B; I _c =100 мА; Р _п <200 мВт; 4.7 к/47 к	SOT323,SC70	B-E-C
p11	PDTA114TT	PHIL	Dono	V _{GB0} =50 B; I _G =100 mA; P _D =200 mBr; h ₂₁ > 200; R ₁ 10 kOm	SOT23.SOD23	B-E-C
P12	DDTA114TCA	DIODS	Dono	V _{DC} =50 B; I _C =100 mA; P _D <200 mBT; R1 10 k	SOT23.SOD23	B·E·C
P12	DDTA114TE	DIODS	Dono	V _{DG} =50 B; I _C =100 mA; P _D <150 mB±; R1 10 k	SOT523	B-E-C
P12	DDTA114TKA	DIODS	Dono	V _{CC} =50 B; I _C =100 мА; Р ₀ <200 мВт; R1 10 к	SOT346.SC59	
P12	DDTA114TUA	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; R1 10 k	SOT323,SC70	SATISFACE OF STREET
p12	PDTC114TT	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 мА; P _D =200 мВт; h ₂₁ >200; R ₁ 10 кОм	SOT23,SOD23	100000000000000000000000000000000000000
P12	SO2906A	SGS	pnp	V _{CBO} =60 B; I _C =150 мA; P _D =300 мBr; h ₂₁ =40120; I _T >200 МГц	SOT23,SOD23	
p13	BB207	PHIL	var×2	$V_B > 15 \text{ B; Ig}(V_B = 15 \text{ B}) < 0.01 \text{ m/s}, I_{21} = 7686 \text{ n/s}; C_{7.58} = 25.529.7 \text{ n/s}$	SOT23,SOD23	
P13	DDTA114ECA	DIODS	Donp	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 10 k/10 k	SOT23,SOD23	
P13	DDTA114EE	DIODS	Dono	V _{DG} =50 B; I _C =100 MA; P _D <200 MB; T0K/10K	SOT523	B·E·C
P13	DDTA114EKA	DIODS	Dono		SOT346.SC59	
P13	7-10-10-12-11-12-12-13-13	7.000		V _{CC} =50 B; I _C =100 mA; P _D < 200 mBT; 10 k/10 k	SOT323.SC70	
	DDTA114EUA		Dpnp	V _{CC} =50 B; I _C =100 MA; P _D <200 MBT; 10 K/10 K		700700
P14	DDTA114YCA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D < 200 mBT; 10 κ/47 κ	SOT23,SOD23	75077 10
P14	DDTA114YE	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _O <150 mBτ; 10 κ/47 κ	SOT523	B-E-C
P14	DDTA114YKA	DIODS		V _{CC} =50 B; I _C =100 mA; P _D <200 mBr; 10 k/47 k	SOT346,SC59	
P14	DDTA114YUA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мА; P _D <200 мВт; 10 к/47 к	SOT323,SC70	
P15	DDTA114WCA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мА; Р _D <200 мВт; 10 к/47 к	SOT23,SOD23	
P15	DDTA114WE		Dpnp	V _{CC} =50 B; I _C =100 мА; Р _D <150 мВт; 10 к/47 к	SOT523	B-E-C
P15	DDTA114WKA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мA; P _D <200 мВт; 10 к/47 к	SOT346,SC59	11000000000
P15	DDTA114WUA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 10 k/47 k	SOT323,SC70	B.E.C





	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
P16	DDTA124TCA	DIODS	Dpnjo	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; R122 k	S0T23,S0D23	B·E·C
P16	DDTA124TE	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <150 mB+; R122 x	SOT523	B·E·C
P16	DDTA124TKA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; R122 κ	SOT346,SC59	B·E·C
P16	DDTA124TUA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мА; Р _О <200 мВт; R122 к	S0T323,SC70	B·E·C
o16	PDTC114ET	PHIL	Dnpn	V _{CBO} =50 B; I _C =50 мA; P _D =250 мВт; h ₂₁ >30; 10 кОм/10 кОм	SOT23,SOD23	B·E·C
P17	DDTA124ECA	DIODS	Donio	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; 22 к/22 к	SOT23,SOD23	B-E-C
P17	DDTA124EE	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <150 mB⊤; 22 κ/22 κ	SOT523	B·E·C
P17	DDTA124EKA	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <200 mB+; 22 k/22 k	SOT346,SC59	B-E-C
P17	DDTA124EUA	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <200 mB+; 22 k/22 k	S0T323.SC70	B·E·C
017	PDTC124ET	PHIL	Dnpn	V _{CBD} =50 B; I _C =100 mA; P _D =250 mBT; h ₂₁ >60; 22 kOm/22 kOm	S0T23,S0D23	
P18	DDTA124XCA	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; 22 κ/47 κ	SOT23.SOD23	
P18	DDTA124XE	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <150 mB+; 22 κ/47 κ	SOT523	B·E·C
P18	DDTA124XKA	DIODS	Donio	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; 22 κ/47 κ	SOT346.SC59	D2000000000000000000000000000000000000
P18	DDTA124XUA	DIODS	Dono	V _{cc} =50 B; I _c =100 mA; P _D <200 mB⊤; 22 κ/47 κ	S0T323.SC70	200000000000000000000000000000000000000
018	PDTC143ZT	PHIL	Dnon	V _{CR0} =50B; I _C =100 mA; P _D =250 mBT; h ₂₁ ≥100; 4.7 κOm/47 κOm	SOT23.SOD23	
P19	DDTA144TCA	DIODS	Donio	V _{CC} =50B; I _C =100 mA; P _D =200 mBT; R147 k	SOT23,SOD23	
P19	DDTA144TCA	DIODS	Dono	V _{CC} =50 B; I _C =100 MA; P _D <200 MB1; R147 K V _{CC} =50 B; I _C =100 MA; P _D <150 MB1; R147 K	SOT523	B-E-C
P19	DDTA144TE	DIODS			SOT346.SC59	
P19			Dpnp	V _{CC} =50B; I _C =100 mA; P _D <200 mBT; R147 k		
	DDTA144TUA	DIODS	Dpnp	V _{CC} =50B; I _C =100 mA; P _D <200 mBT; R147 k	S0T323,SC70	10.1000 1.000
p19	PDTA 143ZT	PHIL	Dpnp	V_{CB0} = 50 B; I_C = 100 mA; P_D = 250 mBT; h_{21} > 100; 4.7 kOm/47 kOm	SOT23,SOD23	150001 100
p1A	PMBT3904	PHIL	npn	V_{CB0} = 60 B; I_C = 200 mA; P_D = 250 mBT; h_{21} = 100300; f_T > 300 MF μ	S0T23,S0D23	
o1A	PMST3904	PHIL	npn	V_{CB0} = 60 B; I_0 = 200 mA; P_0 = 200 mBT; h_{21} = 100300; f_T > 300	S0T323,SC70	
ρ1B	PMBT2222	PHIL	npn	V_{CB0} = 60 B; I_C = 600 mA; P_D = 250 mBT; h_{21} = 100300; f_T > 250 MF $_{II}$	SOT23,SOD23	
o1D	PMBTA42	PHIL	non	V_{CB0} = 300 B; I_C = 500 mA; P_D = 250 mBT; h_{21} > 40; f_T > 50 MFu.	SOT23,SOD23	B·E·C
p1E	PMBTA43	PHIL	npn	V_{CB0} = 200 B; I_C = 500 mA; P_D = 250 mBT; h_{21} > 40; f_T > 50 MFų	SOT23,SOD23	B·E·C
o1F	PMBT5550	PHIL	non	V _{CB0} = 160 B; I _C = 600 mA; P _D =250 mBT; h ₂₁ =60250; f _T =100300	SOT23,SOD23	B.E.C
o1F	PMST5550	PHIL	npn	V _{CB0} = 160 B; I _C = 600 mA; P _D =200 mBT; h ₂₁ =60250; f _T =100300	S0T323,SC70	B-E-C
p1G	PMBTA06	PHIL	npn	V_{C80} =80B; I_C =500 mA; P_0 =250 mBT; h_{21} >50; f_T >100M Γ_H	SOT23,SOD23	B·E·C
o1H	PMBTA05	PHIL	npn	V _{CBO} =60B; I _C =500 мА; P _D =250 мВт; h ₂₁ >50; f _T >100МГц	SOT23,SOD23	B·E·C
o1J	PMBT2369	PHIL	npn	V _{CB0} =40B; I _C =500 mA; P _D =250 mBT; h ₂₁ =40120	SOT23,SOD23	B.E.C
ρ1K	PMBT6428	PHIL	npn	V _{CBO} =60 B; I _C =200 mA; P _D =250 mBT; h ₂₁ =250650; f _T =100700 MFu	SOT23,SOD23	B-E-C
oIL	PMBT6429	PHIL	npn	V _{CB0} =55B; I _C =200 mA; P _D =250 mBt; h ₂₁ =5001250; f _T =100700 MFu	SOT23,SOD23	B-E-C
o1M	PMBTA13	PHIL	dnpn	V _{CR0} =30 B; I _C =300 mA; P _D =250 mBr; h ₂₁ >5000; f _T >125 MFu	SOT23,SOD23	B·E·C
o1N	PMBTA14	PHIL	dnpn	V _{CR0} =30 B; I _C =300 mA; P _D =250 mBr; h ₂₁ >10000; f _T >125 MFu,	SOT23,SOD23	B·E·C
o1P	PMBT2222A	PHIL	non	V _{CB0} =75B; I _C =600 mA; P _D =250 mBt; h ₂₁ =100300; f _T >300 MFu	SOT23.SOD23	
o1Q	PMBT5088	PHIL	non	V _{CB0} =30B; I _C =50 мА; Р ₀ =250 мВт; h ₂₁ =3501400	SOT23,SOD23	B-E-C
o1Q	PMST5088	PHIL	non	V _{CB0} =35B; I _C =50 мA; P _D =200 мBT; h ₂₁ >300900	S0T323.SC70	
oIR	PMST5089	PHIL	non	V _{CR0} =30B; I _C =50 MA; P _D =200 MBT; h ₂₁ >4001200	S0T323.SC70	La comment
P1s	BFR92W	SIEM	non	V _{CB0} =20B; I _C =30 мA; P _D =280 мВт; h ₂₁ =40200; f _T =5000 МГц	S0T323,SC70	2000000
P2	BFR92A	PHIL	non	V _{CR0} =20B; I ₀ =25 MA; P _D =273 MBT; h ₂₁ >40; f _T =4500 MΓ ₁	SOT23.SOD23	
P2	BFR92ALT1	MOT	non	V _{CR0} =20B; I _C =25 MA; P _D =273 MB; ;1 ₂₁ >40; f _T =4500 MΓ ₁	SOT23,SOD23	
P2	BZX84C12T	DIODS	dz	V _Z (I _{ZT} =5 MA)=11.412.7B;Z _{ZT} (I _{ZT} =5 MA)<250 M	S0T523	A·n.c.·K
P2	HSMS2852	HP	shd×2	V _E (I _E =1 MA)<0.25B; C _T =0.3 nΦ	SOT23.SOD23	
P2 P2	100000000000000000000000000000000000000	HP	shd×2		S0T323,SC70	
-	HSMS285C	1.00		V _e (I _F =1 MA) < 0.25B; C _T =0.3 πΦ		150000000000000000000000000000000000000
P2	SST202	SIL	nFET	V _{DS} =40 B;P _D =350 MBT;I _{DSS} =0.94.5 mA; g _F =1 mCm	SOT23,SOD23	1522/151 - 23
P20	DDTA144ECA	DIODS	Dpnp	V _{CC} =50B; I _C =100 mA; P _D <200 mB+; 47 k/47 k	SOT23,SOD23	12 80 10
P20	DDTA144EE	DIODS	Dpnp	V _{CC} =50B; I _C =100 mA; P _D <150 mBT; 47 k/47 k	SOT523	B·E·C
P20	DDTA144EKA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; 47 κ/47 κ	SOT346,SC59	
P20	DDTA144EUA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; 47 к/47 к	S0T323,SC70	70000000
P21	DDTA144VCA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; 47 к/10 к	SOT23,SOD23	
P21	DDTA144VE	DIODS	Dpnjo	V _{CC} =50 B; I _C = 100 mA; P _D < 150 mBT; 47 к/10 к	SOT523	B-E-C
P21	DDTA144VKA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; 47 к/10 к	SOT346,SC59	B-E-C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
P21	DDTA144VUA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D < 200 mBT; 47 k/10 k	SOT323,SC70	B-E-C
P22	DDTA144WCA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мА; Р ₀ < 200 мВт; 47 к/22 к	SOT23,SOD23	B·E·C
P22	DDTA144WE	DIODS	Dpnp	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; 47 к/22 к	SOT523	B·E·C
P22	DDTA144WKA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мА; Р ₀ <200 мВт; 47 к/22 к	SOT346,SC59	B·E·C
P22	DDTA144WUA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мА; Р ₀ <200 мВт; 47 к/22 к	SOT323,SC70	B·E·C
P23	DDTA115TCA	DIODS	Dpnp	V _{CC} =50 B; I _C =100 мА; Р ₀ <200 мВт; R2 100 к	SOT23,SOD23	B-E-C
P23	DDTA115TE	DIODS	Donp	V _{CC} =50 B; I _C =100 мА; Р ₀ <150 мВт; R1 100 к	SOT523	B·E·C
P23	DDTA115TKA	DIODS	Dono	V _{CC} =50 B; I _C =100 мА; P _C <200 мВт; R1 100 к	SOT346,SC59	B·E·C
P23	DDTA115TUA	DIODS	Dono	V _{CC} =50 B; I _C =100 мА; Р _П <200 мВт; R1 100 к	SOT323,SC70	B·E·C
p23	PDTA114TU	PHIL	Donp	V _{GB0} =50 B; I _G =100 mA; P _D =200 mBr; h ₂₁ >200; R ₁ 10 κOm	SOT323,SC70	B·E·C
P24	DDTA115ECA	DIODS	Donp	V _{CC} =50 B; I _C =100 мА; P _D <200 мВт; 100 к/100 к	SOT23,SOD23	B·E·C
P24	DDTA115EE	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; 100 к/100 к	SOT523	B·E·C
P24	DDTA115EKA	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <200 mB⊤; 100 к/100 к	SOT346,SC59	B-E-C
P24	DDTA115EUA	DIODS	Dono	V _{CC} =50 B; I _C =100 MA; P _D <200 MBT; 100 K/100 K	SOT323.SC70	1800 /A D.A
p24	PDTC114TU	PHIL	Dnpn	V _{CR0} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >200; R ₁ 10 kOm		B·E·C
P25	DDTA125TCA	DIODS	Dono	V _{GC} =50 B; I _C =100 mA; P _D < 200 mBT; R1 200 k	SOT23,SOD23	B·E·C
P25	DDTA125TE	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; R1 200 K	SOT523	B·E·C
P25	DDTA125TKA	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; R1 200 k	SOT346.SC59	
P25	DDTA125TUA	DIODS	Dono	V _{CC} =50 B; I _C =100 мА; Р _D <200 мВт; R1200 к		B·E·C
P25	SO3906	SGS	pnp	V _{СВО} =40 B; I _C = 200 мА; P _П =300 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23.SOD23	707 0
P26	DDTA114GCA	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <200 mBr; R2 10 x	SOT23,SOD23	3222 25 2
P26	DDTA114GE	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <150 mBT; R210 k	SOT523	B-E-C
P26	DDTA114GKA	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; R2 10 k	SOT346,SC59	
P26	DDTA114GUA		Dono	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; R2 10 k	SOT323,SC70	
P26	SO3905	SGS	ono	V _{CR0} =40 B; I _C =200 mA; P _D =300 mBr; h ₂₁ =50150; I _T >200 MFu	SOT23.SOD23	-50.00000
P27	DDTA124GCA	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <200 mB _T ; R2 22 K	SOT23,SOD23	5.5.5.5
P27	DDTA124GE	DIODS	Dono	V _{CC} =50 B; I _C =100 MA; P _D <250 MBT; R222 K	SOT523	B·E·C
P27	DDTA124GKA	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <100 mBT; R222 k	S0T346,SC59	
P27	DDTA124GUA	DIODS		V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; R222 k	SOT323.SC70	
p27	PDTC114YT	PHIL	Dnpn	V _{CR0} =50 B; I _C =100 mA; P _D =200 mBT; H=222K V _{CR0} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >100; 10 kOm/47 kOm	SOT23,SOD23	200000000
P28	DDTA144GCA	DIODS	Dono	V _{CC} =50 B; I _C =100 мА; P _D =200 мВт; R2 47 к	SOT23,SOD23	100000000
P28	DDTA144GE		Dono	V _{CC} =50 B; I _C =100 mA; P _D <200 mBT; R2-47 K	SOT523	B-E-C
P28	DDTA144GKA	DIODS	Dono	V _{CC} =50 B; I _C =100 mA; P _D <100 mBT; R247 K	SOT346,SC59	1000000 000
P28	DDTA144GNA	DIODS	Dono	V _{CC} =50 B; I _C =100 MA; P _D <200 MB1; R247 K	SOT323,SC70	
P29	DDTA115GCA	DIODS	Dono	V _{CC} =50 B; I _C =100 MA; P _D <200 MBT; R2100 K	SOT23,SOD23	
P29	DDTA115GE	DIODS	Dono	V _{CC} =50 B; I _C =100 MA; P _D <200 MBT; R2100 K	SOT523	B·E·C
P29	DDTA115GKA	DIODS	Dono	V _{CC} =50 B; I _C =100 MA; P _D <200 MBT; R2:100 K	SOT346.SC59	Salta Control
P29	DDTA115GUA	DIODS	7.1		SOT323,SC70	100000000000000000000000000000000000000
029	PDTA114YT	PHIL	Dono	V _{CC} =50 B; I _C =100 mA; P _C <200 mB _T ; R2100 k	SOT23,SOD23	0.000000
p29 p2A	PMBT3906	PHIL	Dpnp	V _{CB0} =50 B; I _C =100 mA; P _D =200 mB _T ; h ₂₁ >100; 10 kOm/47 kOm	SOT23,SOD23	2000
p2A p2A	PMST3906	PHIL	pnp	V _{CB0} =40 B; I _C =200 mA; P _D =250 mB; h ₂₁ =100300; f _T >250 MF _U	SOT323,SOD23	
-	PMBT2907	PHIL	pnp	V _{CB0} =40 B; I _C =200 mA; P _D =200 mB _T ; h ₂₁ =100300; f _T >250 MF _U	SOT23,SOD23	
p2B		PHIL	pnp	V _{CB0} =60 B; I _C =600 мA; P _D =250 мBτ; h ₂₁ >30; f _T >200 MΓц		
p2D	PMBTA92	PHIL	pnp	V _{CB0} =300 B; I _C =500 мА; P _D =250 мВт; h ₂₁ >40; f ₁ >50 МГц	SOT23,SOD23	
p2E	PMBTA93		pnp	V _{CB0} =200 B; I _C =500 MA; P _D =250 MBT; h ₂₁ >40; f _T >50 MFu	SOT23,SOD23	1,000-000-004
p2F	PMBT2907A	PHIL	pnp	V _{CB0} =60 B; I _C =600 мA; P _D =250 мBτ; h ₂₁ >50; f _T >200 MΓц	SOT23,SOD23	195,077 99
p2G	PMBTA56	PHIL	pnp	V _{CB0} =80 B; I _C =500 мА; P _D =250 мВт; h ₂₁ >50; f _T >50 МГц	SOT23,SOD23	12000 100 1
p2H	PMBTA55	PHIL	pnp	V _{CB0} =60 B; I _C =500 мА; P _D =250 мВт; h ₂₁ >50; f _T >50 МГц	SOT23,SOD23	
p2L	PMBT5401		pnp	V _{CB0} =160 B; I _C =500 MA; P _D =250 MBT; h ₂₁ =60240; f _T =100300 MF _U	SOT23,SOD23	
p2L	PMST5401	PHIL	pnp	V _{CB0} =160 B; I _C =500 мA; P _D =200 мВт; h ₂₁ =60240; f _T =100300 МГц	SOT323,SC70	A
P2p	BFR92AW	PHIL	npn	V _{CB0} =20 B; I _C =25 mA; P _D =273 mBt; h ₂₁ >40; f _T =4500 MFu	SOT323,SC70	
p2T	PMBT4403	PHIL	pnp	V _{CB0} =40 B; I _C =600 мA; P _D =250 мВт; h ₂₁ =100300; f _T >200 МГц	SOT23,SOD23	
p2T	PMST4403	PHIL	pnp	V_{CB0} =40 B; I_C =600 mA; P_D =200 mBT; h_{21} =100300; f_T >200 M Γ_{II}	SOT323,SC70	R.F.C





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
o2U	PMBTA63	PHIL	dpnp	V_{CB0} =30 B; I_C =500 mA; P_D =250 mBt; h_{21} >5000; f_T >125 MFu	SOT23,SOD23	B-E-C
2V	PMBTA64	PHIL	dpnp	V_{C80} =30B; I_C =500 mA; P_0 =250 mBT; h_{21} >10000; f_T >125 MFu	SOT23,SOD23	B·E·C
o2X	PMBT4401	PHIL	npn	V_{CB0} =40 B; I_C =600 mA; P_0 =250 mBr; h_{21} =100300; f_T >250 MFц	SOT23,SOD23	B·E·C
o2X	PMST4401	PHIL	npn	V _{CB0} =60B; I _C =600 мА; P _D =200 мВт; h ₂₁ =100300; f _T >250 МГц	SOT323,SC70	B·E·C
P3	BZX84C13T	DIODS	dz	V _Z (I _{ZT} =5mA)=12.414.1B;Z _{ZT} (I _{ZT} =5mA)<300m	SOT523	A·n.c.·K
P3	TP0202T	SIL	pMOS	V _{DS} =20 B;I _D =410 mA;P _D =350 mBT;Q _F =600 mCm; R _{DSfont} =0.9 Om	SOT23,SOD23	G-S-D
P3	TP0202T	TEMIC	pMOS	V _{DS} =20 B;I _D =410 mA;P _D =350 mBT;Q _F =600 mCm; R _{DSfont} =0.9 Om	SOT23,SOD23	G·S·D
030	PDTC114YU	PHIL	Dnpn	V _{GB0} =50B; I _C =100 mA; P _D =200 mBt; h ₂₁ >100; 10 kOm/47 kOm	SOT323,SC70	B-E-C
031	PDTA143XT	PHIL	Donio	V _{CRD} =50B; I _C =100 мA; P _D =250 мВт; h ₂₁ >50; 4.7 кОм/10 кОм	SOT23,SOD23	B·E·C
032	PDTC143XT	PHIL	Dnpn	V _{CB0} =50B; I _C =100 mA; P _D =250 mBt; h ₂₁ >50; 4.7 kOm/10 kOm	SOT23,SOD23	B·E·C
P32	S05400	SGS	pnp	V_{CB0} = 130 B; I_C = 600 mA; P_D = 200 mBT; h_{21} = 40180; f_T > 100 MFu	SOT23,SOD23	B·E·C
P33	S05401	SGS	pnp	V _{GB0} = 160 B; I _G = 600 мA; P _D =200 мВт; h ₂₁ =60240; f _T > 100 МГц	SOT23,SOD23	B·E·C
P38	SST4338	SIL	nFET	V _{DS} =50B;P _D =300 mBT;I _{DSS} < 0.6 mA; g _F >0.6 mCm	SOT23,SOD23	D·S·G
P39	S0692	SGS	pnp	V _{сво} =300 B;I _C =100 мА; P _о =310 мВт; h ₂₁ >40; f _T >50 МГц	SOT23,SOD23	B·E·C
P39	SST4339	SIL	nFET	V _{DS} =50B;P _D =300 MBT;I _{DSS} <0.8 mA;g _F >1.5 mCm	SOT23.SOD23	D-S-G
P3W	MMBF2202PT1	MOT	pMOS	V _{DS} =20B;I _D =300 mA; P _D =150 mBT; R _{DS(co)} =3.5 0m	SOT323,SC70	
P4	BFR92R	PHIL	non	V _{CB0} =20B; I _C =30 мA; P _D =280 мВт; h ₂₁ =40200; f ₁ =5000 МГц	SOT23,SOD23	
P4	BZX84C15T	DIODS	dz	V _Z (I _{ZT} =5 MA)=13.815.6B;Z _{ZT} (I _{ZT} =5 MA)<30 OM	SOT523	A·n.c.·K
P4	SST204	SL	nFET	V _{DS} =25 B;P _D =350 mBT;I _{DSS} =0.23 mA;g _E =0.5 mCm	SOT23,SOD23	10.000000000000000000000000000000000000
P40	SST4340	SIL	nFET	V _{DS} =50B;P _D =300 mBT;I _{DSS} <1.3 mA;g _F >9 mCm	SOT23.SOD23	
P41	SST4341	SIL	nFET	V _{DS} =50B;P _D =300 MBT;I _{DSS} <2 MA;g _F >1.5 MCM	SOT23.SOD23	15.152
046	PDTA143XU	PHIL	Dono	V _{CB0} =50B; I _C =100 MA; P _D =250 MBT; h ₂₁ >50; 4.7 KOM/10 KOM	SOT323,SC70	
047	PDTA143ZU	PHIL	Dpnp	V _{CB0} =50B; I _C =100 мA; P _D =250 мBт; h ₂₁ >100; 4.7 кОм/47 кОм	SOT323,SC70	
04F	PMBD353	PHIL	shd×2	V _B <4B; I _E <30 mA; V _E (I _E =10 mA)<600 mB; C _D <1 πΦ	SOT23,SOD23	100000000000000000000000000000000000000
P5	BFR92AR	PHIL	non	V _{CR0} =20B, I _C =25 мA; P _C =273 мBт; h ₂₁ >40; f _T =4500 МΓц	SOT23.SOD23	
P5	BZX84C16T	DIODS	dz	V ₂ (I _{2T} =5 MA)=15.317.1B;Z ₂₇ (I _{2T} =5 MA)<40 OM	SOT523	Arn.c.+K
P5	FMMT2369A	ZETEX	non	V _{CB0} =40B; I _C =200 mA; P _D =330 mBr; h ₂₁ =40120	SOT23,SOD23	101,000,000
053	PDTC143XU	PHIL	Dnon	V _{CB0} =50B;I _C =100 mA;P ₀ =250 mBr;h ₂₁ >50;4.7 кOm/10 кOm	SOT323,SC70	
o54	PDTC143ZU	PHIL	Dnon	V _{CPD} =50B; I _C =100 mA; P _D =250 mBr; h ₂₁ >100; 4.7 κOm/47 κOm	SOT323.SC70	
055	PDTA114YU	PHIL	Dono	V _{CB0} =50B; I _C =100 MA; P _D =200 MBT; h ₂₁ >100; 10 KOM/47 KOM	SOT323.SC70	
P57	SST5457	SIL	nFET	V _{DS} ⁻ 25B; P _D ⁻ 310 MBT; I _{DSS} ⁻ 15 MA; G _F <1 MCM	SOT23,SOD23	
P58	SST5458	SIL	nFET	V _{DS} =25B;P _D =310 мВт;I _{DSS} =15 мА;Q _E <1.5 мСм	SOT23,SOD23	1000001 100
P59	SST5459	SIL	nFET	V _{DS} -25B,P _D -310 MBT, I _{DSS} -13 MA, g _E < 1.3 MCM V _{DS} -25B;P _D -350 MBT; I _{DSS} -416 MA; g _E < 2 MCM	SOT23,SOD23	
05A	PMBD6050	PHIL	fd		SOT23,SOD23	7 7 7
μüΑ	PMBDGGGG	PHIL	IU	$V_R < 70 B$; $I_F < 215 \text{ mA}$; $V_F (I_F = 150 \text{ mA}) < 1.25 B$; $I_R < 100 \text{ mA}$; $C_D < 1.5 \text{ n}\Phi$; $I_{BB} < 4 \text{ mc}$	30123,30023	A-II.CK
p5B	PMBD6100	PHIL	fd×2	V_R < 70 B; I_F < 215 MA; V_P (I_F = 100 MA) = 0.851.1 B; I_R < 100 HA; C_0 < 1.5 n Φ ; I_{BR} < 4 HC	SOT23,SOD23	A1+A2+K1,K2
05C	PMBD7000	PHIL	fd×2	$V_R < 100 B; I_F < 2.15 \text{mA}; V_F (I_F = 100 \text{mA}) = 0.75 1.25 B; I_R < 500 \text{mA}; C_B < 1.5 \text{n} \Phi; I_{BB} < 4 \text{mc}$	S0T23,S0D23	A1 • K2 • K1,A2
05D	PMBD914	PHIL	fd	V _B <70 B; I _F <215 мA; V _E (I _F =150 мA) ≤ 1.25 B; Iобр ≤ 1 мкA; C _D ≤1.5 nΦ; I _{BB} <4 HC	S0T23,S0D23	A•n.c.•K
p5G	PMBD352	PHIL	shd×2	V _B <4B; I _E <30 mA; V _E (I _E =10 mA)<600 mB; C _D <1 nΦ	SOT23,SOD23	A1 · K2 · K1, A2
P6	BZX84C18T	DIODS	dz	V _Z (I _{ZT} =5 mA)=16.819.1B;Z _{ZT} (I _{ZT} =5 mA)<45 Om	SOT523	A•n.c.•K
P63	SST5463	SIL	pFET	V _{DS} =60B;P _D =310 мВт;I _{DSS} >5 мА;g _E =14 мСм	SOT23,SOD23	D·S·G
P64	SST5464	SIL	pFET	V _{DS} =60B;P _D =310 мBт;I _{DSS} =29 мA;g _E <5 мСм	SOT23,SOD23	D·S·G
P65	SST5465	SIL	pFET	V _{DS} =60B;P _D =310 мBт;I _{DSS} =416 мA; g _E <6 мСм	SOT23,SOD23	D·S·G
06A	PMBF4416	PHIL	nFET	V _{DS} =30B;I _{DSS} =15мA;P _D =250мВт;g _F <7.5мСм	SOT23,SOD23	S·D·G
06B	PMBF5484	PHIL	nFET	V _{DS} =25B;I _{DSS} =5mA;P _D =250 mBT; g _E <6 mCm	SOT23,SOD23	S·D·G
06G	PMBF4393	PHIL	nFET	V _{DS} =40B;I _{DSS} =5мA; P _D =250 мВт; R _{DS(eD)} < 100 Ом	SOT23,SOD23	D·S·G
06H	PMBF5486	PHIL	nFET	V _{DS} =25B;I _{DSS} =15 мА; Р _D =250 мВт; g _F <8 мСм	SOT23,SOD23	200.000
o6J	PMBF4391	PHIL	nFET	V _{DS} =40B; I _{DSS} =50 MA; P _D =250 MBT; R _{DS(en)} <30 OM	SOT23,SOD23	1000000
						32000 33
06K	PMBF4392	PHIL	nFET	V _{DS} =40B; I _{DSS} =25 mA; P _D =250 mBT; R _{DS(on)} <60 Om	SOT23.SOD23	D-5-G

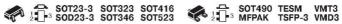
Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
06S	PMBFJ176	PHIL	pFET	V _{DS} =30B;I _{DSS} >2 MA;P _D =300 MBT;R _{DS(on)} <250 OM	SOT23,SOD23	D·S·G
6W	PMBFJ175	PHIL	pFET	V _{DS} =30B;I _{DSS} >7 MA;P _D =300 MBT;R _{DS(opt} <125 OM	SOT23,SOD23	D·S·G
06X	PMBFJ174	PHIL	pFET	V _{DS} =30 B; I _{DSS} >20 mA; P _D =300 mBr; R _{DS(co)} < 85 Om	SOT23,SOD23	D·S·G
06Y	PMBFJ177	PHIL	pFET	V _{DS} =30B; I _{DSS} >1.5 mA; P _D =300 mBT; R _{DS(DD)} <300 Om	SOT23,SOD23	D·S·G
P7	BZX84C20T	DIODS	dz	V ₂ (I _{ZT} =5mA)=18.821.2B; Z _{ZT} (I _{ZT} =5mA)<550m	SOT523	A·n.c.·K
p7Y	PDTB123YT	PHIL	Dpnp	V _{GB0} =50 B; I _G =500 мА; P _D =250 мВт; h ₂₁ >70; 2.2 кОм/10 кОм	SOT23,SOD23	B-E-C
P8	BZX84C22T	DIODS	dz	V ₂ (I _{ZT} =5 mA)=20.823.3B; Z _{ZT} (I _{ZT} =5 mA)<55 Om	SOT523	A·n.c.·K
P8A	FLLD261	ZETEX	d×2	V _B <100 B; I _E < 250 мА; V _E (I _E = 200 мА) < 1.4 B; I _B <5 мкА; С _D <4 пФ	SOT23,SOD23	A1-K2-K1,A2
P8A	FLLD261	FAIR	d×2	V _B <100 B; I _F < 250 мА; V _F (I _F = 200 мА) < 1.4 B; I _B <5 мкА; С _D <4 пФ	SOT23,SOD23	A1-K2-K1,A2
p8A	PMBZ5226B	PHIL	dz	$V_2\{I_{Z1}$ = 20 mA) = 3.3 B; $I_L\{V_R$ = 1.0 B} < 25 mKA; $Z_{Z1}\{I_{Z1}$ = 20 mA) < 1600 Om; I_{ZM} = 200 mA	SOT23,SOD23	A•n.c.•K
p8B	PMBZ5227B	PHIL	dz	$V_2\{I_{ZT}=20 \text{ mA}\}=3.6 \text{ B}; I_L\{V_R=1.0 \text{ B}\}<15 \text{ mKA}; Z_{ZT}\{I_{ZT}=20 \text{ mA}\}<1700 \text{ Om}; I_{ZM}=200 \text{ mA}$	SOT23,SOD23	A•n.c.•K
p8C	PMBZ5228B	PHIL	dz	$V_2(I_{ZT} = 20 \text{ mA}) = 3.9 \text{ B}; I_L(V_R = 1.0 \text{ B}) \le 10 \text{ m/A}; Z_{ZT}(I_{ZT} = 20 \text{ mA}) \le 1900 \text{ Om}; I_{ZM} = 200 \text{ mA}$	SOT23,SOD23	A·n.c.·K
p8D	PMBZ5229B	PHIL	dz	$V_2(I_{ZT}$ = 20 mA) = 4.3 B; $I_L(V_R$ = 1.0 B) < 5 mKA; $Z_{ZT}(I_{ZT}$ = 20 mA) < 2000 Om; I_{ZM} = 200 mA	SOT23,SOD23	A·n.c.·K
p8E	PMBZ5230B	PHIL	dz	$V_2(I_{ZT}$ =20 mA)=4.7 B; $I_1(V_R$ =1.0 B) < 5 mrA; $Z_{ZT}(I_{ZT}$ =20 mA) < 2000 Om; I_{ZM} =200 mA	SOT23,SOD23	A•n.c.•K
p8F	PMBZ5231B	PHIL	dz	$V_2(I_{ZT}$ =20 mA)=5.1 B; $I_L(V_R$ =2.0 B) < 5 mrA; $Z_{ZT}(I_{ZT}$ =20 mA) < 2000 Om; I_{ZM} =200 mA	SOT23,SOD23	A·n.c.·K
p8G	PMBZ5232B	PHIL	dz	$V_Z(I_{ZT}$ = 20 mA) = 5.6 B; $I_L(V_R$ = 3.0 B) < 5 mKA; $Z_{ZT}(I_{ZT}$ = 20 mA) < 1600 OM; I_{ZM} = 200 mA	SOT23,SOD23	A·n.c.·K
р8Н	PMBZ5233B	PHIL	dz	$V_Z(I_{ZT}$ = 20 mA) = 6.0 B; $I_L(V_R$ = 3.5 B) < 5 mKA; $Z_{ZT}(I_{ZT}$ = 20 mA) < 1600 O m; I_{ZM} = 200 mA	SOT23,SOD23	A·n.c.·K
08J	PMBZ5234B	PHIL	dz	$V_Z(I_{ZT}$ = 20 mA) = 6.2 B; $I_L(V_R$ = 4.0 B) < 5 mKA; $Z_{ZT}(I_{ZT}$ = 20 mA) < 1000 O m; I_{ZM} = 200 mA	SOT23,SOD23	A·n.c.·K
p8K	PMBZ5235B	PHIL	dz	$V_Z(I_{ZT}$ =20 mA)=6.8 B; $I_L(V_R$ =5.0 B)<3 mrA; $Z_{ZT}(I_{ZT}$ =20 mA)<750 Om; I_{ZM} =200 mA	SOT23,SOD23	A•n.c.•K
p8L	PMBZ5236B	PHIL	dz	$V_2(I_{ZT}=20 \text{ mA})=7.5 \text{ B}; I_L(V_R=6.0 \text{ B}) \le 3 \text{ mrA}; Z_{ZT}(I_{ZT}=20 \text{ mA}) \le 500 \text{ Om}; I_{ZM}=200 \text{ mA}$	SOT23,SOD23	A·n.c.·K
M8q	PMBZ5237B	PHIL	dz	$V_Z(I_{ZT}$ = 20 mA) = 8.2 B; $I_L(V_R$ = 6.5 B) < 3 mKA; $Z_{ZT}(I_{ZT}$ = 20 mA) < 500 Om; I_{ZM} = 200 mA	SOT23,SOD23	A•n.c.•K
p8N	PMBZ5238B	PHIL	dz	$V_2(I_{ZT}$ = 20 mA) = 8.7 B; $I_L(V_R$ = 6.5 B) < 3 mkA; $Z_{ZT}(I_{ZT}$ = 20 mA) < 600 Om; I_{ZM} = 200 mA	SOT23,SOD23	A•n.c.•K
p8P	PMBZ5239B	PHIL	dz	$V_Z(I_{ZT}$ = 20 mA) = 9.1 B; $I_L(V_R$ = 7.0 B) < 3 mrA; $Z_{ZT}(I_{ZT}$ = 20 mA) < 600 Om; I_{ZM} = 200 mA	SOT23,SOD23	A·n.c.·K
p8Q	PMBZ5240B	PHIL	dz	$V_2(I_{Z1} = 20 \text{ mA}) = 10 \text{ B; } I_1(V_R = 8.0 \text{ B}) \le 3 \text{ m/A; } Z_{Z1}(I_{Z1} = 20 \text{ mA}) \le 600 \text{ Om; } I_{ZM} = 200 \text{ mA}$	SOT23,SOD23	A•n.c.•K
p8R	PMBZ5241B	PHIL	dz	$V_Z(I_{ZT}$ = 20 mA) = 11 B; $I_L(V_R$ = 8.4 B) < 2 mxA; $Z_{ZT}(I_{ZT}$ = 20 mA) < 600 Om; I_{ZM} = 200 mA	SOT23,SOD23	A•n.c.•K
p8S	PMBZ5242B	PHIL	dz	$V_Z(I_{Z1}$ = 20 mA) = 12 B; $I_L(V_R$ = 9.1 B) < 1 mrA; $Z_{Z1}(I_{Z1}$ = 20 mA) < 600 Om; I_{ZM} = 200 mA	SOT23,SOD23	A·n.c.·K
p8T	PMBZ5243B	PHIL	dz	$V_Z(I_{ZT}$ = 9.5 mA) = 13 B; $I_L(V_R$ = 9.9 B) < 0.5 m kA; $Z_{ZT}(I_{ZT}$ = 9.5 mA) < 600 Om; I_{ZM} = 200 mA	SOT23,SOD23	A·n.c.·K
p8U	PMBZ5244B	PHIL	dz	$V_Z(I_{ZT}$ =9.0 mA)=14B; $I_L(V_R$ =10B)<0.1 mkA; $Z_{ZT}(I_{ZT}$ =9.0 mA)<600 Om; I_{ZM} =200 mA	SOT23,SOD23	A·n.c.·K
V8c	PMBZ5245B	PHIL	dz	$V_Z(I_{ZI}$ = 8.5 mA) = 15B; $I_L(V_B$ = 11B) < 0.1 mxA; $Z_{ZI}(I_{ZI}$ = 8.5 mA) < 600 Om; I_{ZM} = 200 mA	SOT23,SOD23	A·n.c.·K
W8c	PMBZ5246B	PHIL	dz	$V_2(I_{ZT}$ =7.8 mA)=16B; $I_2(V_{ST}$ =12B)<0.1 mrA; $Z_{ZT}(I_{ZT}$ =7.8 mA)<600 Om; I_{ZM} =200 mA	SOT23,SOD23	A·n.c.·K
0 8 X	PMBZ5247B	PHIL	dz	V _Z (I _{ZT} =7.4 mA)=17B;I _L (V _B =13B)<0.1 mkA;Z _{ZT} (I _{ZT} =7.4 mA)<600 Om; I _{ZM} =200 mA	SOT23,SOD23	A•n.c.•K
o8Y	PMBZ5248B	PHIL	dz	$V_Z(I_{ZT}=7.0 \text{ mA})=18 \text{ B}; I_L(V_R=14 \text{ B})<0.1 \text{ m/sA}; Z_{ZT}(I_{ZT}=7.0 \text{ mA})<600 \text{ Om}; I_{ZM}=200 \text{ mA}$	SOT23,SOD23	A•n.c.•K
p8Z	PMBZ5249B	PHIL	dz	$V_2(I_{ZT}=6.6 \text{ mA})=19 \text{ B}; I_2(V_{R}=14 \text{ B})<0.1 \text{ mkA}; Z_{ZT}(I_{ZT}=6.6 \text{ mA})<600 \text{ Om}; I_{ZM}=200 \text{ mA}$	SOT23,SOD23	A·n.c.·K
P9	BCX70KR	ZETEX	npn	V _{GB0} =45 B; I _G =200 мА; P _D =330 мВт; h ₂₁ =380630; f _T >250 МГц	SOT23,SOD23	B-E-C





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
P9	BCX70KR	PHIL	npn	V _{CR0} =45B; I _C =200 mA; P _D =330 mBT; h ₂₁ =380630; f _T >250 MFu,	SOT23,SOD23	C·B·E
P9	BZX84C24T	DIODS	dz	V ₂ (I _{2T} =5 mA)=22.825.6B;Z _{2T} (I _{2T} =5 mA)<70 Om	SOT523	A+n.c.+K
P9	DAP222	ON	di×2	V _B <80 B; I _E <300 mA; P _D <150 mBr; V _E (I _E =100 mA)<1.2 B; t _{BB} <4 hc	S0T416,SC75A	K1-K2-A1,A2
09A	PLVA650A	PHIL	dz	V _Z (I _{ZT} = 250 niKA) = 4.85.2 B; I ₁ (V _B = 0.8°V _Z) < 20 niKA; Z _{ZT} (I _{ZT} = 250 niKA) < 700 On; I _{ZM} = 250 mA	SOT23,SOD23	A·n.c.·K
o9B	PLVA653A	PHIL	dz	V _Z (_{ZT} 250 mKA) = 5.15.5 B; l ₁ (V _B = 0.8*V _Z) < 5 mKA; Z _{ZT} (I _{ZT} 250 mKA) < 250 OM; I _{ZM} 250 mA	SOT23,SOD23	A•n.c.•K
09C	PLVA656A	PHIL	dz	$V_Z(l_{ZT}$ = 250 m/cA) = 5.45.8 B; $I_L(V_R$ = 0.8 °V_Z) < 1 m/cA; $I_{ZT}(l_{ZT}$ = 250 m/cA) < 100 Om; I_{ZM} = 250 m/A	SOT23,SOD23	A+n.c.+K
09D	PLVA659A	PHIL	dz	$V_2 V_{27}$ = 250 m(A) = 5.76.1 B; $I_1 (V_R = 0.8^* V_2) < 500$ HA; $I_2 V_1 = 250$ M(A) < 100 OM; $I_2 V_2 = 250$ MA	SOT23,SOD23	A+n.c.+K
o9E	PLVAG62A	PHIL	dz	$V_Z(I_{ZT}^-250 \text{ m/s.A})=6.06.4 \text{ B; }I_z(V_R^-0.8^+V_Z) < 100 \text{ HA; } Z_Z(I_{ZT}^-250 \text{ m/s.A}) < 100 \text{ Om; }I_{ZM}^-250 \text{ m/s.A}$	SOT23,SOD23	A•n.c.•K
o9F	PLVA665A	PHIL	dz	$V_Z(I_{ZT}^-250 \text{ m/s}A)=6.36.7 \text{ B; }I_z(V_R^-0.8^*V_Z)<50 \text{ m/s}; \\ Z_Z(I_{ZT}^-250 \text{ m/s}A)<100 0 \text{ m; }I_{ZM}^-250 \text{ m/s}$	SOT23,SOD23	A•n.c.•K
p9G	PLVA668A	PHIL	dz	$V_Z(I_{ZT}$ = 250 m/cA)= 6.67.0 B; $I_L(V_R$ = 0.8 V_Z) < 10 HA; $I_Z(I_{LT}$ = 250 m/cA) < 100 Om; I_{ZM} = 250 m/c	SOT23,SOD23	A+n.c.+K
o9J	PLVA2650A	PHIL	dz×2	$V_Z(I_{ZT}$ = 250 nikA)= 4.85.2 B; $I_L(V_R$ = 0.8* V_Z) < 20 nikA; $I_{ZT}(I_{ZT}$ = 250 nikA) < 700 On; I_{ZM} = 250 nik	SOT23,SOD23	K1 • K2 • A1,A2
o9K	PLVA2653A	PHIL	dz×2	$V_Z(I_{ZT}^-250 \text{ nicA}) = 5.15.5 \text{ B; } I_z(V_R^-0.8^+V_Z^-) \le 5 \text{ nicA;}$ $Z_Z(I_{ZT}^-250 \text{ nicA}) \le 250 \text{ nicA};$	SOT23,SOD23	K1-K2-A1,A2
p9L	PLVA2656A	PHIL	dz×2	$V_Z(I_{ZT}$ = 250 m/cA)=5.45.8 B; $I_L(V_R$ =0.8 ° V_Z) < 1 m/cA; $I_{ZT}(I_{ZT}$ = 250 m/cA)< 100 Om; I_{ZM} = 250 m/c	SOT23,SOD23	K1+K2+A1,A2
9M	PLVA2659A	PHIL	dz×2	$V_z I_{ZT}$ = 250 nikA) = 5.76.1 B; $I_1 (V_R = 0.8^* V_Z) < 500 \text{ HÅ};$ $Z_z I_{ZT} = 250 \text{ mkA} < 100 0m; I_{ZM} = 250 mA$	SOT23,SOD23	K1•K2•A1,A2
o9N	PLVA2662A	PHIL	dz×2	$V_Z(I_{ZT}$ = 250 mKA}=6.06.4 B; $I_L(V_R$ =0.8* V_Z } < 100 HA; $I_{ZT}(I_{ZT}$ =250 mKA}< 100 Om; I_{ZM} =250 mA	SOT23,SOD23	K1 • K2 • A1,A2
090	PLVA2665A	PHIL	dz×2	V _Z (I _{ZT} = 250 m/cA) = 6.3 6.7 B; I _L (V _R = 0.8 °V _Z) < 50 n/A; Z _Z (I _{ZT} = 250 m/cA) < 100 Om; I _{ZM} = 250 m/A	SOT23,SOD23	K1+K2+A1,A2
09P	PLVA2668A	PHIL	dz×2	$V_Z(I_{ZT}$ = 250 m(A) = 6.67.0 B; $I_L(V_R$ = 0.8* V_Z } < 10 HA; $I_{ZT}(I_{ZT}$ = 250 m(A) < 100 0m; I_{ZM} = 250 mA	SOT23,SOD23	K1 • K2 • A1,A2
PA	2SC4666	TOSH	npn	V_{CB0} = 50 B; I_C = 150 mA; P_D = 100 mBT; h_{21} >600 1800; f_T = 250 MFu	S0T323,SC70	B·E·C
PA	BA885	INF	pin	$V_R < 50 \text{ B; } I_F < 50 \text{ mA; } V_F (I_F = 50 \text{ mA}) < 1.1 \text{ B; } I_R < 0.05 \text{ mkA; } C_0 < 0.4 \text{ m}$	SOT23,SOD23	A+n.c.+K
pA2	PMBD2836	PHIL	fd×2	$V_R < 75B$; $I_F < 215$ mA; $V_R (I_F = 150$ mA) < 1.25 B; $I_R < 100$ mA; $C_D < 2.5$ m Φ ; $I_{RR} < 4$ mC.	SOT23,SOD23	K1+K2+A1,A2
pA3	PMBD2835	PHIL	fd×2	$V_R < 35B; I_F < 215 \text{ MA}; V_R (I_F^* 150 \text{ MA}) < 1.25 B; I_R < 100 \text{ HA}; C_D < 2.5 \text{ n}\Phi; t_{RR} < 4 \text{ Hz}$	SOT23,SOD23	K1-K2-A1,A2
pA5	PMBD2837	PHIL	fd×2	V_R <30 B; I_F <215 MA; V_R (I_F = 150 MA)<1.25 B; I_R <100 HA; C_D <2.5 n Φ ; I_{RR} <4 HC	SOT23,SOD23	A1+A2+K1,K2
pA6	PMBD2838	PHIL	fd×2	$V_R < 50 B_i I_F < 215 mA_i V_R (I_F = 150 mA_i) < 1.25 B_i I_R < 100 mA_i C_0 < 2.5 m\Phi_i I_R = 4 mC_0 < 4.5 mA_i < 4.00 mA_$	SOT23,SOD23	A1+A2+K1,K2
PB	2SC4666	TOSH	npn	V_{CB0} =50 B; I_C =150 mA; P_D =100 mBT; h_{21} >12003600; f_T =250 MFu,	SOT323,SC70	B-E-C
PC	BA886	INF	pin	$V_R \le 50 \text{ B; } I_E \le 50 \text{ mA; } V_E (I_E = 50 \text{ mA}) \le 1.15 \text{ B; } I_R \le 0.05 \text{ mkA; } C_D \le 0.2 \text{ n} \Phi$	SOT23,SOD23	A·n.c.·K
PC	MGSF1P02L	ON	pMOS	V _{DS} =20B; I _D =750 мA; P _D =400 мВт; R _{DS(on)} <0.5 Ом	SOT23,SOD23	G·S·D
PD	2SA1171D	REN	pnp	V _{CBD} =90 B; I _C =50 mA; P _D =150 mBT; h ₂₁ =250500	SOT23,SOD23	B·E·C
PD	BSS84L	MOT	pMOS	V _{DS} =50 B;I _D =130 мA;P _D =360 мВт; g _E =50 мСм; R _{DS(col} =10 Ом	SOT23,SOD23	G·S·D
PDs	BA887	INF	pin	$V_B \le 50 \text{ B; } I_F \le 100 \text{ mA; } I_B \le 0.02 \text{ m/A; } C_D \le 0.27 \text{ m}$	SOT23,SOD23	A•n.c.•K
PE	2SA1171E	REN	pnp	V _{CB0} =90B; I _C =50 mA; P _D =150 mBT; h ₂₁ =400800	SOT23,SOD23	B·E·C
oG1	PMBT5551	PHIL	npn	V _{CB0} = 180 B; I _C =600 mA; P _D =250 mBT; h ₂₁ =80250; f _T =100300	S0T23,S0D23	B·E·C
PH	KRA307	KEC	pnp	V _{CR0} =50B; I _C =100 mA; P _D =100 mBT; R ₁ /R ₂ =10/47 kOm	SOT323,SC70	B·E·C
PH2	SST4302	SIL	nFET	V _{DS} =30B;P _D =300 мBт;I _{DSS} >5 мA;g _E >1 мCм	SOT23,SOD23	D·S·G
PH3	SST4303	SIL	nFET	V _{DS} =30B;P _D =300 MB; I _{DSS} >10 MA;Q _E >2 MCM	S0T23.S0D23	1200000 000
PH4	SST4304	SIL	nFET	V _{DS} =30B;P _D =300 MBT;I _{DSS} >15 MA;Q _E >2 MCM	S0T23.S0D23	1000000 100
PI	KRA308	KEC	pnp	V _{CPO} =50 B; I _C =100 мА; P _D =100 мВт; R ₁ /R ₂ =22/47 кОм	S0T323,SC70	V 20 30
		REN	nFET	V _{GS} >22 B; I _D =50 MA; P _D =150 MBT; Q _F >20 MCM; I _{DSS} =614 MA	SOT23,SOD23	
PIB	2SK1070B					

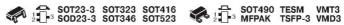
Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
ID	2SK1070D	REN	nFET	V _{GS} >22 B; I _D =50 mA; P _D =150 mBT; g _F >20 mCm; I _{DSS} =1830 mA	SOT23,SOD23	S·D·G
IE.	2SK1070E	REN	nFET	V _{SS} >22 B; I _D =50 MA; P _D =150 MBT; g _E >20 MCM; I _{DSS} =2740 MA	SOT23,SOD23	S·D·G
eJ	KRA309	KEC	onp	V _{GBO} = 50 B; I _G = 100 mA; P _D = 100 mBT; R ₁ /R ₂ = 47/22 kOm	SOT323,SC70	B·E·C
oJ1	BSH101	PHIL	nMOS	V _{DS} =60B;I _D =700 MA;P _D =500 MBT;R _{DS/ont} <0.6 OM	SOT23,SOD23	G·S·D
oJ2	BSH102	PHIL	nMOS	V _{ns} =30B;I _n =1A	SOT23,SOD23	G-S-D
oJ3	BSH103	PHIL	nMOS	V _{DS} =30 B;I _D =850 mA;P _D =500 mBT;R _{DSion} <0.5 0m	SOT23,SOD23	G·S·D
PMs	BAR66	INF	pin×2	V _B < 150 B; I _E < 200 мA; V _E (I _E =50 мA) < 1.2 B; C _D < 0.35 пФ	SOT23,SOD23	A1-K2-K1.A2
p04	PMBS3904	PHIL	ngn	V _{GR0} =60 B; I _G =100 mA; P _D =250 mBT; h ₂₁ =100300; f _T >180 MF _U	SOT23,SOD23	B·E·C
006	PMBS3906	PHIL	ana	V _{GB0} =40 B; I _G = 100 мА; P _D =250 мВт; h ₂₁ =100300; f _T >150 МГц	SOT23,SOD23	
POs	BAR64	SIEM	pin	V _B < 200 B; I _E < 100 MA; V _E (I _E =50 MA) < 1.1 B; C _D < 0.35 пФ	SOT23,SOD23	
PPs	BAR6404	SIEM	pin×2	V _B <200 B; I _E <100 mA; V _E (I _E =50 mA)<1.1 B; C _D <0.35 пФ	SOT23,SOD23	
PPs	BAR64-04	INF	oin×2	V _B <150 B; I _E <100 мА; V _E (I _E =50 мА)<1.1 B; C _D <0.35 пФ	SOT23,SOD23	-
PPs	BAR64-04W	INF	pin×2	V _B <150 B; I _F <100 мА; V _E (I _F =50 мА)<1.1 B; C _D <0.35 пФ	SOT323,SC70	
PPs	BAR64-04W	INF	pin×2	V _R <150 B; I _F <100 MA; V _F (I _F =50 MA)<1.1 B; C _D <0.35 nΦ	SOT416.SC75A	
PRs	BAR6405	SIEM	pin×2	V _B <200 B; I _E <100 mA; V _E (I _E =50 mA)<1.1 B; C _D <0.35 πΦ	SOT23,SOD23	
PRs	BAR64-05	INF	pin×2	V _R <150 B; I _F <100 mA; V _E (I _F =50 mA)<1.1 B; C _D <0.35 πΦ	SOT23,SOD23	
PRs	BAR64-05W	INF	pin×2	V _R <150 B; I _E <100 mA; V _E (I _E =50 mA)<1.1 B; C _D <0.35 πΦ	SOT323,SC70	
PS	TP0101TS	SIL	oMOS	V _{DS} =20 B; I _D =1000 mA; P _D =1000 mBτ; Q _E =1300 mCm; R _{DS(m)} =0.65 Om	SOT23,SOD23	
PSs	BAR6406	SIEM	pin×2	V _B <200 B; I _F <100 MA; V _E (I _F =50 MA)<1.1 B; C _D <0.35 πΦ	SOT23,SOD23	
PSs	BAR64-06	INF	pin×2	V _R <150 B; I _F <100 MA; V _E (I _F :50 MA)<1.1 B; C _D <0.35 πΦ	SOT23,30D23	100 CONTRACTOR 1000
PSs	BAR64-06W	INF	pin×2		SOT323,SC70	No. of the last of
PV	1SV294	SANYO		V _B <150 B; I _E <100 mA; V _B (I _E =50 mA)<1.1 B; C _D <0.35 nΦ	SOT23,SOD23	
pV3	BAT54A	PHIL	pin shd×2	V _R >50 B; I _F <50 MA; V _F (I _F =50 MA)=0.920.97 B; I _R <0.1 MKA		
oV4	BAT54S	PHIL	shd×2	V _R <30 B; I _F <200 MA; V _F (I _F =30 MA)<500 MB; C _D <10 nΦ; t _{RR} <5 hc	SOT23,SOD23 SOT23,SOD23	
	-0000-0000		-100	V _R <30 B; I _F <200 mA; V _F (I _F =30 mA)<500 mB; C _D <10 nΦ; t _{RR} <5 hc		
pW1	BAT54C	PHIL	shd×2	V _R <30 B; I _F <200 mA; V _F (I _F =30 mA)<500 mB; C _D <10 mΦ; t _{RR} <5 hc	SOT23,SOD23	
Q0		MCHIP	mrc	V _{TR} =4.625B;V _{DD} =15.5B;I _{DD} <60 mKA		RST-VDD-VSS
Q2	MMBC1321Q2	MOT	npn	V _{CB0} =30 B;I _C =10 mA;h ₂₁ =4080	SOT23,SOD23	
Q3	MMBC1321Q3	MOT	npn	V _{CB0} =30 B; I _C =10 mA; h ₂₁ =60120	SOT23,SOD23	
Q4	MMBC1321Q4	MOT	npn	V _{CB0} =30 B; I _C =10 mA; h ₂₁ =90180	SOT23,SOD23	
Q5	MMBC1321Q5	MOT	npn	V _{CB0} =30 B; I _C =10 mA; h ₂₁ =135270	SOT23,SOD23	
QA	RN1421	TOSH	Dnpn	V_{CEO} =50 B; I_C =800 mA; P_O =200 mBT; f_T >250 MF $_U$; B_1/B_2 =1/1 kOm	SOT346,SC59	10000000
QAA	BC846AF	AUK	npn	V _{CB0} =80 B; I _C = 100 мА; P _D =200 мВт; h ₂₁ =110220; f _T =150 МГц	SOT490,SC89	
QAB	BC846BF	AUK	npn	V_{CB0} =80 B; I_C =100 mA; P_D =200 mBT; h_{21} =200450; I_T =150 M Γ_{IJ}	SOT490,SC89	
QAC	BC846CF	AUK	npn	V_{CB0} =80 B; I_C = 100 mA; P_D =200 mBT; h_{21} =420800; f_T =150 MF μ	SOT490,SC89	
QB	RN1422	TOSH	Dnpn	V_{CE0} =50 B; I_C =800 mA; P_D =200 mBT; f_T >250 MFu; R_1/R_2 =2.2/2.2 kOm	SOT346,SC59	
QC	RN1423	TOSH	Dnpn	V_{CE0} =50 B; I_C =800 mA; P_0 =200 mBr; f_T >250 MFu; R_1/R_2 =4.7/4.7 kOm	SOT346,SC59	Salara Cara
QD	RN1424	TOSH	Dnpn	V_{CE0} =50 B; I_C =800 mA; P_0 =200 mBt; f_T >250 MFu; R_1/R_2 =10/10 kOm	SOT346,SC59	2000000000
QE	RN1425	TOSH	Dnpn	V_{CEO} =50 B; I_C =800 mA; P_D =200 mBT; f_T >250 MFц; R_1/R_2 =0.47/10 кОм	SOT346,SC59	120000000
QF	RN1426	TOSH	Dnpn	V_{CE0} =50 B; I_C =800 mA; P_0 =200 mBt; f_T >250 MFu; R_1/R_2 =1/10 kOm	SOT346,SC59	
QG	RN1427	TOSH	Dnpn	V_{CE0} =50 B; I_C =800 mA; P_D =200 mBT; f_T >250 MFu; R_1/R_2 =2.2/10 kOm	SOT346,SC59	
QI	2SC4196	REN	npn	V _{GBO} =25 B; I _C =50 мА; Р _D =150 мВт; h ₂₁ =50180; f _T >1.8 ГГц	SOT346,SC59	
QI	2SC4261	REN	npn	V _{GBO} =25 B; I _C =50 мА; Р _D =100 мВт; h ₂₁ =50180; f ₁ >1.8 ГГц	SOT323,SC70	
QJ	MCP100T-270/TT		mrc	V _{TR} =2.625 B; V _{DD} =15.5 B; I _{DD} <60 мкA	SOT23,SOD23	
QK	MCP100T-300/TT	200	mrc	V _{TR} =2.925B;V _{DD} =15.5B;I _{DD} <60 мкA	SOT23,SOD23	
QL	MCP100T-315/TT	MCHIP	mrc	V _{TR} =3.075 B;V _{DD} =15.5 B;I _{DD} <60 мкA	SOT23,SOD23	
QM	MCP100T-450/TT	MCHIP	mrc	V _{TR} =4.375B;V _{DD} =15.5B;I _{DD} <60 mrA	SOT23,SOD23	
QN	MCP100T-460/TT	MCHIP	mrc	V _{TR} =4.475B;V _{DD} =15.5B;I _{DD} <60 m/A	SOT23,SOD23	RST-VDD-VS
20	KTC4080	KEC	npn	$V_{CB0}=40 \text{ B; } I_C=20 \text{ mA; } P_0=100 \text{ mBt; } h_{21}=70140; f_T>550 \text{ MFu}$	SOT323,SC70	B.E.C
QΡ	MCP100T-485/TT	MCHIP	mrc	V _{TB} =4.725B;V _{DD} =15.5B;I _{DD} <60 мкA	SOT23,SOD23	RST-VDD-VS
QR	KTC4080	KEC	npn	V _{CB0} =40 B; I _C =20 mA; P _D =100 mBr; h ₂₁ =4080; f _T >550 MFu	SOT323,SC70	
ργ	KTC4080	KEC	npn	V _{GB0} =40 B; I _G =20 мA; P _D =100 мВт; h ₂₁ =100200; f _T >550 МГц		B-E-C
RO	MCP101T-475/TT	10000	mrc	V _{тв} =4.625B;V _{то} =15.5B;I _{по} <60 мкА	SOT23,SOD23	73.7.173





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3
R01	KSR1101	SAMS	Dnpn	V _{CB0} =50 B; I _C =100 мА; P _D =200 мВт; h ₂₁ >20; f _T >250 МГц	SOT23,SOD23	B·E·C
R02	KSR1102	SAMS	Dnpn	V_{CP0} =50 B; I_C =100 mA; P_D =200 mBr; h_{21} >30; f_T >250 M Γ_{IJ}	SOT23,SOD23	B·E·C
R03	KSR1103	SAMS	Dnpn	V _{сво} =50B; I _c =100 мА; P ₀ =200 мВт; h ₂₁ >56; f _T >250 МГц	SOT23,SOD23	B·E·C
R04	KSR1104	SAMS	Dnon	V _{CPD} =50B; I _C =100 mA; P _D =200 mBt; h ₂₁ >68; f _T >250 MFц	SOT23.SOD23	B-E-C
R05	KSR1105	SAMS	Dnpn	V _{CRD} =50B; I _C =100 mA; P _D =200 mBt; h ₂₁ >30; f _T >250 MFц	SOT23,SOD23	B·E·C
R06	KSR1106	SAMS	Dnpn	V _{стро} =50 B; I _с =100 мА; P _D =200 мВт; h ₂₁ >68; f _T >250 МГц	SOT23,SOD23	B·E·C
R07	KSR1107	SAMS	Dnpn	V _{сво} =50 B; I _c =100 мА; P _o =200 мВт; h ₂₁ >68; f _T >250 МГц	SOT23,SOD23	B·E·C
R08	KSR1108	SAMS	Dnpn	V _{CR0} =50 B; I _C =100 mA; P _D =200 mBt; h ₂₁ >56; f _T >250 MF _U	SOT23,SOD23	B·E·C
R09	KSR1109	SAMS	Dnon	V _{CBO} =40 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =100600; f _T >250 МГц	SOT23.SOD23	
R1	BFR93	SGS	non	V _{CB0} =20B; I _C =50 мA; P _D =300 мВт; h ₂₁ =50200; f ₁ =5500 МГц	SOT23.SOD23	
R1	BZX84C4V7T	DIODS	dz	V _Z (I _{ZT} =5 MA)=4.45.0 B; Z _{ZZ} (I _{ZT} =5 MA) < 80 OM	SOT523	A·n.c.·K
R1	HSMS-8101	HP	shd	V _{BR} >4B;V _E (I _E =1 мA) < 0.35B;C _D <0.26πΦ;R _D =14 0м	SOT23.SOD23	
R1	TN2010T	SIL	nMOS	V _{DS} = 200 B; I _D = 120 мA; P _D = 360 мВт; Q _F = 300 мСм; R _{DSI onl} = 9.5 Ом	SOT23.SOD23	0.000
R10	KSR1110	SAMS	non	V_{CB0} =40 B; I_C =100 mA; P_0 =200 mBr; I_{24} =100600; I_T >250 MFu	SOT23.SOD23	V2500000000
R11	KSR1111	SAMS	non	V_{CB0} =40 B; I_C =100 mA; P_D =200 mBr; I_{PD} =100600; I_T >250 MFu	SOT23,SOD23	(C) (C)
R12	KSR1112	SAMS	non	V _{CR0} =40 B; I _C =100 MA; P _D =200 MB; H ₂₁ =100600; I _T >250 MFu	SOT23,SOD23	
R13	2SC4885	NEC			S0T323,SC70	
			npn	V _{CBO} =25B; I _C =50 мA; P _D =120 мBr; h ₂₁ =60150; f _T >2.5ГГц		
R13	KSR1113	SAMS	Dnpn	V _{CB0} =50 B; I _C =100 мА; Р _D =300 мВт; h ₂₁ >56; f _T >250 МГц	SOT23,SOD23	
R14	KSR1114	SAMS	Dnpn	V_{CB0} =50B; I_C =100 mA; P_D =300 mBT; h_{21} >68; f_T >250 MFu	SOT23,SOD23	
R1A	MMBT3904	VISH	npn	V _{CB0} =60 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =100300; f _T >300 МГц	SOT23,SOD23	
R1A	MMST3904	ROHM	npn	V _{CB0} =60B; I _C =200 мА;h ₂₁ =100300; f _T >250 МГц	SOT346,SC59	
R1A	SST3904	ROHM	npn	V _{CB0} =60B; I _C =200 мA; h ₂₁ =100300; f _T >300 МГц	SOT23,SOD23	
R1A	UMT3904	ROHM	npn	V_{CB0} =60 B; I_{C} =200 mA; P_{D} =200 mBT; h_{21} >100; f_{T} >300 MFu,	SOT323,SC70	
RIB	MMST2222	ROHM	non	V_{CB0} =60 B; I_C =600 мA; h_{21} =100300; f_T >250 МГц	SOT346,SC59	B·E·C
R1B	SST2222	ROHM	npn	V_{CB0} =60B; I_C =600 mA; h_{21} =100300; f_T >250M Γ_{IL}	SOT23,SOD23	
R1C	MMST1130	ROHM	non	V _{CB0} =30 B; I _C =200 mA; h ₂₁ =120360	SOT346,SC59	B.E.C
R1C	MMSTA20	ROHM	npn	V_{CB0} =40 B; I_C =200 mA; h_{21} >120; f_T >125 M Γ u	SOT346,SC59	B·E·C
R1C	SST1130	ROHM	npn	V _{CB0} =30 B; I _C =200 мА;h ₂₁ =120360	SOT23,SOD23	B·E·C
R1C	SSTA20	ROHM	npn	V_{CB0} =40B; I_C =200 MA ; h_{21} >120; f_T >125 $M\Gamma U_L$	SOT23,SOD23	B·E·C
R1G	MMBTA06	VISH	non	V_{CB0} =80B; I_C =300 mA; P_0 =350 mBT; h_{21} >50; f_T >100 MFu	SOT23,SOD23	B·E·C
RIG	MMSTA06	ROHM	npn	V_{CB0} =80 B; I_C =500 mA; h_{21} >100; f_T >100 MF μ	SOT23,SOD23	B·E·C
RIG	MMSTA06	ROHM	non	V _{CBD} =80 B; I _C =500 mA; h ₂₁ >100; f _T >100 MF _H	SOT346,SC59	B·E·C
RIG	SSTA06	ROHM	non	V _{CR0} =80 B; I _C =500 mA; h ₂₁ > 100; f _T > 100 MΓ _U	SOT23,SOD23	B·E·C
RIH	MMBTA05	VISH	non	V _{CR0} =60B; I _C =30 MA; P _D =350 MBT; h ₂₁ >50; f _T >100 MFu	SOT23.SOD23	B·E·C
R1H	SSTA05	ROHM	non	V _{CPD} =60 B; I _C =500 mA; h ₂₁ > 100; f ₁ > 100 MFu	SOT23,SOD23	B·E·C
RIJ	SST6427	ROHM	non	V _{CR0} =40 B; I _C =500 mA; h ₂₁ =20000200000	SOT23.SOD23	
R1K	MMST6428	ROHM	non	V _{cpn} =60B; I _c =200 мA; h ₂₁ =250650; f _T >100 MΓιμ	SOT23,SOD23	
R1K	MMST6428	ROHM	non	V _{CB0} =60B; I _C =200 mA; I ₂ =250650; I ₁ >100 MΓ _L	SOT346.SC59	
R1K	SST6428	ROHM	non	V _{CR0} -60B; I _C -200 MA; I _{D2} -250650; I _T >100 MI _L	SOT23.SOD23	200000000
R1M	MMBTA13	VISH	dnpn	V _{CB0} =30 B; I _C =300 MA; P _O =350 MBT; h ₂₁ >10000; f _T >125 MΓц	SOT23,SOD23	
R1M	MMSTA13	ROHM	dnpn	V _{CR0} -30B; I _C -300 MA; P _D -300 MB; I _{T2} > 10000; I _T > 125 MFu	SOT23,SOD23	
RIM RIM	MMSTA13	ROHM	dnpn	V _{CB0} =30B; I _C =500 MA; N ₂₁ > 10000; N ₇ > 125 MFц V _{CB0} =30B; I _C =500 MA; N ₂₁ > 10000; N ₇ > 125 MFц	SOT346,SC59	
R1M	SSTA13	ROHM	non	170	SOT23,SOD23	
R1N	MMBTA14	VISH	- pro-	V _{CB0} =30 B; I _C =500 MA; h ₂₁ >10000; f ₁ >125 MFu	SOT23,SOD23	
	100000000000000000000000000000000000000		dnpn	V _{CB0} =30B; I _C =300 MA; P _D =350 MB; h ₂₁ >20000; f _T >125 MΓμ	Live Control of the C	100000000000000000000000000000000000000
R1N	MMSTA14	ROHM	dnpn	V _{CBO} =30 B; I _C =500 мА; h ₂₁ >20000; f ₇ > 125 МГц	SOT23,SOD23	
RIN	MMSTA14	ROHM	dnpn	V _{CB0} =30 B; I _C =500 mA; h ₂₁ >20000; f ₁ >125 MF _L	SOT346,SC59	
R1N	SSTA14	ROHM	npn	V_{C80} =30B; I_C =500 mA; h_{21} >20000; f_T >125M Γ_{II}	SOT23,SOD23	
R10	MMST5088	ROHM	npn	V _{CB0} =35B; I _C =200 mA; h ₂₁ =300900; f _T >50 M Γ _U	SOT23,SOD23	
310	MMST5088	ROHM	npn	V _{CB0} =35B; I _C =200 мА; h ₂₁ =300900; f ₁ >50 МГц	SOT346,SC59	
RIP	MMBT2222A	VISH	npn	V_{CB0} =50B; I_C =800 mA; P_D =200 mBT; h_{21} =100300; f_T >200 MF μ	SOT23,SOD23	
R1P	MMST2222A	ROHM	non	V _{CB0} =75B; I _C =600 мA; h ₂₁ =100300; f _T >250 МГц	SOT346,SC59	12222
RIP	SST2222A	ROHM	non	V _{CR0} =75B; I _C =600 мA; h ₂₁ =100300; f _T >250МГц	SOT23,SOD23	B-E-C

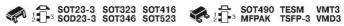
Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
RIP	UMT2222A	ROHM	npn	V _{GB0} =75 B; I _C =800 mA; P _D =500 mB1; h ₂₁ > 30	SOT323,SC70	B·E·C
R1Q	SST5088	ROHM	npn	V _{CB0} =35 B; I _C =200 мА; h ₂₁ =300900; f _T >50 МГц	SOT23.SOD23	B-E-C
RIR	MMST5089	ROHM	npn	V _{CB0} =30 B; I _C =200 мА; h ₂₁ =4001200; f _T >50 МГц	SOT346,SC59	B-E-C
RIR	SST5089	ROHM	npn	V _{CR0} =30 B; I _C =200 MA; h ₂₁ =4001200; f _T >50 MF _L	SOT23.SOD23	B-E-C
12	2SC2351P	NEC	npn	V _{CR0} =25 B; I _C =70 mA; P _D =250 mBt; h ₂₁ =40120; f _T =4.5 fTu	SOT23,SOD23	B·E·C
32	2SC4225	NEC	non	V _{CB0} =25 B; I _C =70 мА; Р _П = 160 мВт; h ₂₁ =40120; f _T =4ГГц	SOT323,SC70	B-E-C
12	BFR93A	PHIL	non	V _{GB0} =20 B; I _G =50 мА; P _D =300 мВт; h ₂₁ =50200; f _T =5500 МГц	SOT23,SOD23	235552 TS
32	BFR93ALT1	MOT	non	V _{GB0} =20 B; I _G =50 mA; P _D =300 mBt; h ₂₁ =50200; f _T =5500 MFu	SOT23,SOD23	
22	BZX84C5V1T	DIODS	dz	V _Z (I _{ZT} =5mA)=4.85.4B;Z _{ZT} (I _{ZT} =5mA)<60 Om		A·n.c.·K
323	2SC3356Q	NEC	ngn	V _{CB0} =20 B; I _C =100 mA; P _D =200 mBr; h ₂₁ =50100; I _T =7 ΓΓц	SOT23,SOD23	
123	2SC4226	NEC	npn	V _{GB0} *20 B; I _G * 100 мА; P _D * 150 мВт; h ₂₁ *4080; f _T >3 ГГц	SOT323.SC70	
124	2SC3356R	NEC	non	V _{GB0} *20 B; I _G * 100 мА; Р _D *200 мВт; h ₂₁ *80160; f _T *7 ГГц	SOT23.SOD23	(7.50.00.00.00.00.00.00.00.00.00.00.00.00.
224	2SC4226	NEC	npn	V _{CB0} =20 B; I _C =100 MA; P _D =150 MBT; h ₂₁ =70140; f _T >3 ΓΓ _U	SOT323.SC70	
125	2SC3356S	NEC	npn	V _{CB0} =20 B; I _C =100 MA; P _D =200 MBT; h ₂₁ =125250; f _T =7 ITI _L	SOT23,SOD23	180077 57
125	2SC4226	NEC	npn	V _{CBB} =20 B; I _C =100 MA; P _D =150 MBT; h ₂₁ =125250; f _T >3 FT _U	SOT323,SC70	-
120 12A	ADR380ART	AD	vref	V _{IN} =2.418B; I _{CLIT} =5MA; V _{CLIT} =2.048B	SOT23,SOD23	
1ZH	ADIODUAN	AU	ale)	VIN-2.4 16 B, IOUT-3 MA, VOUT-2.046 B	30123,30023	GND
R2A	MMBT3906	VISH	ono	V _{CR0} =40 B; I _C =100 MA; P _D =200 MBT; h ₂₁ =100300; f _T >250 MFu	SOT23,SOD23	B·E·C
12A	MMST3906	ROHM	ono	V _{GB0} =40 B; I _C =200 MA; I ₁₂₁ =100300; I _T >250 MF _L	SOT346,SC59	B·E·C
12A	SST3906	ROHM	onp	V _{CR0} =40 B; I _C =200 MA; h ₂₁ =100300; f _T >250 MFu	SOT23,SOD23	
12A	UMT3906	ROHM	pnp	V _{CB0} =40 B; I _C =200 мA; P _D =200 мВт; h ₂₁ > 100; f ₁ > 250 МГц	SOT323,SC70	1000000 500
12B	MMST2907	ROHM	ono	V _{CB0} =60 B; I _C =600 mA; h _{P1} =100300; f _T >200 MFu	SOT346.SC59	
12B	SST2907	ROHM	onp	V _{CB0} =60 B; I _C =600 mA; h _{P1} =100300; f _T >200 MFu	SOT23,SOD23	
32C	MMSTA70	ROHM	pnp	V _{CR0} =60 B; I _C = 200 MA; h ₂₁ = 160400; f _T > 125 MF _L	SOT23,SOD23	
2C	MMSTA70	ROHM	pnp	V _{CB0} =60 B; I _C =200 мA; h ₂₁ =160400; f _T >125 MFu	SOT346,SC59	
12F	MMST2907A	ROHM	pnp	V _{CB0} =60 B; I _C =600 MA; I _D =100300; I _T >200 MFu	SOT346.SC59	
12F	SST2907A	ROHM	pnp	V _{CB0} =60 B; I _C =600 MA; h ₂₁ =100300; f _T >200 MFu	SOT23,SOD23	CO. C.
12F	UMT2907A	ROHM	ono	V _{GB0} =60 B; I _G =600 мА; P _G =200 мВ; h ₂₁ > 100; f ₇ > 200 МГц	SOT323.SC70	100000
12G	MMSTA56	ROHM	ono	V _{CBB} =80 B; I _C =500 мA; h ₂₁ > 100; f _T >50 МГц	SOT23,SOD23	22/22/27/2
12G	MMSTA56	ROHM	one	V _{CB0} =80 B; I _C =500 мA; h ₂₁ > 100; η > 50 МГц	SOT346.SC59	
12G	SSTA56	ROHM		V _{CB0} =80 B; I _C =500 MA; h ₂₁ > 100; r ₇ >50 MF _L	SOT23,SOD23	
12G 12H	SSTA55	ROHM	pnp	0.00	SOT23,SOD23	
12H 12K	Not proposed to	ROHM	3 - 1	V _{CB0} =60 B; I _C =500 мA; h ₂₁ > 100; f ₁ >50 MFц	The Control of Control	12222
	MMST8598		pnp	V _{GB0} =60 B; I _C =200 MA; h ₂₁ =100300; f _T >150 MF _L	SOT23,SOD23	
12K	MMST8598	ROHM	pnp	V _{GB0} =60 B; I _C =200 MA; h ₂₁ =100300; f _T >150 MF _U	SOT346,SC59	
20	MMST5087	ROHM	pnp	V_{CB0} =50 B; I_C =200 mA; h_{21} =250800; f_T >40 M Γ_{IJ}	SOT23,SOD23	
220	MMST5087	ROHM	pnp	V _{CB0} =50 B; I _C =200 μA, h ₂₁ =250800; f _T >40 ΜΓ _Ц	S0T346,SC59	
12P	MMST5086	ROHM	pnp	V_{CB0} =50 B; I_C =200 mA; h_{21} =150500; f_T >40 M Γ_{IJ}	SOT23,SOD23	
12P	MMST5086	ROHM	pnp	V_{CB0} =50 B; I_C =200 mA; h_{21} =150500; f_T >40 MF $_{II}$	SOT23,SOD23	10000000
12P	MMST5086	ROHM	pnp	V _{CB0} =50 B; I _C =200 мА; h ₂₁ =150500; f _T >40 МГц	SOT346,SC59	100000000
12Q	SST7157	ROHM	pnp	V _{CB0} =60 B; I _C =200 mA; h ₂₁ > 100	SOT346,SC59	2.45Sc/A - DZ
12s	BFR93A	SIEM	npn	V _{CB0} =20 B; I _C =50 мA; P _D =300 мВт; h ₂₁ =50200; f _T =5500 МГц	SOT23,SOD23	
12s	BFR93AW	SIEM	npn	V _{CB0} =20 B; I _C =50 мA; P _D =300 мВт; h ₂₁ =50200; f _T =5500 МГц	SOT323,SC70	
?2T	MMBT4403	VISH	pnp	V_{CB0} =40 B; I_C =800 mA; P_D =200 mBt; h_{21} =100300; f_T >200 M Γ_U	SOT23,SOD23	
?2T	MMST4403	ROHM	pnp	V_{CB0} = 40 B; I_C = 600 mA; h_{21} = 100300; f_T > 200 M Γ_{IL}	SOT346,SC59	
?2T	SST4403	ROHM	pnp	V_{CB0} =40 B; I_C =600 mA; h_{21} =100300; f_T >200 MFu	SOT23,SOD23	200000000000
12T	UMT4403	ROHM	pnp	V_{CB0} =40 B; I_C =600 mA; P_D =200 mBt; h_{21} >100; f_T >200 MFц	SOT323,SC70	
?2U	MMSTA63	ROHM	dpnp	V _{CB0} =30 B; I _C =300 мА; h ₂₁ > 5000; f _T > 125 МГц	SOT346,SC59	B-E-C
12U	SSTA63	ROHM	pnp	V ₀₈₀ =30 B; I _C =300 мА; h ₂₁ >5000; f _T > 125 МГц	SOT23,SOD23	B-E-C
?2V	MMSTA64	ROHM	dpnp	V_{CB0} =30 B; I_C =300 мA; h_{21} >10000; f_T >125 МГц	SOT23,SOD23	B-E-C
2V	MMSTA64	ROHM	dpnp	V_{CB0} =30 B; I_C =300 mA; h_{21} >10000; f_T >125 M Γ_{II}	SOT346,SC59	B·E·C
?2V	SSTA64	ROHM	pnp	V_{CB0} =30 B; I_C =300 mA; h_{21} >10000; f_T >125 MFu	SOT23,SOD23	B·E·C
72X	MMBT4401	VISH	npn	V _{CB0} =50 B; I _C =800 mA; P _D =200 mB1; h ₂₁ =100300; f _T >200 MFu	SOT23,SOD23	B-E-C





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
R2X	MMST4401	ROHM	npn	V _{CB0} =60 B; I _C =600 мА; h ₂₁ =100300; f _T >250 МГц	SOT346,SC59	B-E-C
R2X	SST4401	ROHM	npn	V _{CB0} =60 B; I _C =600 мА; h ₂₁ =100300; f ₁ >250 МГц	S0T23,S0D23	B·E·C
R2X	UMT4401	ROHM	npn	V _{CB0} =60 B; I _C =600 мА; P _D =200 мВт; h ₂₁ >100; f _T >250 МГц	S0T323,SC70	B·E·C
R2Z	SST4400	ROHM	npn	V _{CR0} =60B; I _C =600 MA; h ₂₁ =50150; f _T >200 MF _U	SOT23,SOD23	B·E·C
R3	2SC2351Q	NEC	non	V _{CB0} =25B; I _C =70 MA; P _D =250 MBT; h ₂₁ =100200; f _T =4.5 ITI ₄	SOT23,SOD23	B·E·C
R3	2SC4225	NEC	npn	V _{CBO} =25B; I _C =70 мA; P _D =160 мВт; h ₂₁ =100200; f _T =4ГГц	S0T323,SC70	B·E·C
R3	BZX84C5V6T	DIODS	dz	V ₇ (I ₂₇ =5 MA)=5.26.0 B; Z ₇₇ (I ₂₇ =5 MA) < 40 OM	S0T523	A•n.c.•K
R30A	REF3012AIDBZ	TI	vref	V _{IN} =1.85.5 B;I _{OUT} =25 MA; V _{OUT} =1.25 B	SOT23,SOD23	IN-OUT-GND
R30B	REF3020AIDBZ	TI	vref	V _{IN} =1.85.5 B;I _{OUT} =25 MA; V _{OUT} =2.048 B	SOT23.SOD23	IN-OUT-GND
R30C	REF3025AIDBZ	П	vref	V _{IN} =1.85.5 B;I _{OUT} =25 MA; V _{OUT} =2.5 B	SOT23.SOD23	IN-OUT-GND
	REF3033AIDBZ	TI	vref	V _{IN} =1.85.5 B;I _{OUT} =25 MA; V _{OUT} =3.3B	SOT23.SOD23	
R30E	REF3040AIDBZ	TI	vref	V _{IN} =1.85.5 B;I _{OUT} =25 MA; V _{OUT} =4.096 B	SOT23.SOD23	IN-OUT-GND
	REF3030AIDBZ	TI	vref	V _{IN} =1.85.5 B;I _{DUT} =25 MA; V _{DUT} =3.0 B	SOT23.SOD23	
R33	2SC3583Q	NEC	non	V _{CB0} =20B; I _C =65 MA; P _D =200 MBT; h ₂₁ =50100; f _T =9 ΓΓ _U	S0T23.S0D23	100000000000000000000000000000000000000
R33	2SC4227	NEC	non	V _{CR0} =20B; I _C =65 MA; P _D =150 MBT; h ₂₁ =4090; f _T >4.5 ΓΓц	S0T323.SC70	
R34	2SC3583R	NEC	non	V _{CR0} =20B; I _C =65 MA; P _D =200 MBT; h ₂₁ =80160; f _T =9 ΓΓ _U	S0T23,S0D23	
R34	2SC4227	NEC	non	V _{CBD} =20B; I _C =65 MA; P _D =150 MBT; h ₂₁ =70150; f _T >4.5 ΓΓ _U	S0T323,SC70	
R35	2SC3583S	NEC	non	V _{CBD} =20B; I _C =65 MA; P _D =130 MBT; I _{D2} =70130; I _D =4.311I _L V _{CBD} =20B; I _C =65 MA; P _D =200 MBT; I _{D2} =125250; I _T =9 FF _L	SOT23.SOD23	
R35	2SC4227	NEC	non	V _{CB0} =20B; I _C =65 мA; P _D =150 мВт; h ₂₁ =110240; f _T >4.5 ГГц	SOT323,SC70	
R3A	ADR381ART	AD	vref	V _{IN} =2.818B; I _{OUT} =5MA; V _{OUT} =2.5B	SOT23,SOD23	
R3B	MMST918	ROHM	non	V _{CB0} =30 B; I _C =50 мA; h ₂₁ >20650; f _T =600 МГц	SOT23.SOD23	B·E·C
R3B	SST918	ROHM	non	V _{CR0} =30B; I _C =50 MA; h ₂₁ >75; f _T >600 MΓu	SOT23,SOD23	
R4	BFR93R	TELEF	non	V _{CB0} =20B; I _C =50 мA; P _D =300 мBτ; h ₂₁ =50200; f _T =5500 MΓц	SOT323.SC70	
R4	BZX84C6V2T	DIODS	dz	V _Z (I _{ZT} =5 MA)=5.86.6B;Z _{Z1} (I _{ZT} =5 MA) < 10 OM	SOT523	A•n.c.•K
R43	2SC3585Q	NEC	non	V _{CRO} =20B; I _C =35 MA; P _D =200 MBT; h ₂₁ =50100; f _T =10 FF _L	SOT23,SOD23	200000000000000000000000000000000000000
R43	2SC4228	NEC	non	V _{CR0} =20B; I _C =35 MA; P _D =150 MBT; I _D =50100; f _T >5.5 FF _U	S0T323,SC70	100000000000000000000000000000000000000
R44	2SC3585R	NEC	non	V _{CBD} =20B; I _C =35 MA; P _D =200 MBT; I _D =80160; I _T =10 ГГц	SOT23.SOD23	
R44	2SC4228	NEC	non	V _{CB0} =20B, I _C =35 мA; P _D =150 мВт; h ₂₁ =80160; f _T >5.5 ГГц	S0T323,SC70	120000
R45	2SC3585S	NEC	non	V _{CB0} =20B; I _C =35 MA; P _D =130 MBT; I _{D2} =30100; I _T =3.51TI _L V _{CB0} =20B; I _C =35 MA; P _D =200 MBT; I _{D2} =30100; I _T =10 ΓΓ _L	SOT23.SOD23	
R45	2SC4228	NEC	non	V _{CB0} =20B; I _C =35 MA; P _D =150 MBT; I ₂₁ =125250; I _T =1611 I _L	S0T323.SC70	
R5	BFR93AR	SGS	non	V _{CB0} =20B; I _C =50 mA; P _D =300 mB;; I ₂₁ =50200; f ₁ =5500 MFц	SOT23,SOD23	
R5	BZX84C6V8T	DIODS	dz	V _Z (I _{ZZ} =5 MA)=6.47.2 B;Z _{ZZ} (I _{ZZ} =5 MA)<150M	SOT523	A+n.c.+K
R51	KSR2101	SAMS	Dono	V _{CP0} =50B; I _C =100 мA; P _D =200 мBτ; h ₂₁ >20; f _T >250MΓц	SOT23.SOD23	10.000000000000000000000000000000000000
R52	KSR2101	SAMS	Donio		SOT23,SOD23	700071172
R53	KSR2102 KSR2103	SAMS		V _{CB0} =50B; I _C =100 мА; Р _D =200 мВт; Н ₂₁ >30; f _T >250МГц	SOT23,SOD23	
R54	KSR2103	SAMS	Dpnp	V _{CB0} =50B; I _C =100 мА; Р _D =200 мВт; h ₂₁ >56; f _T >250МГц	SOT23,SOD23	
			Dpnp	V _{CBO} =50 B; I _C =100 мА; Р _D =200 мВт; h ₂₁ >68; f _T >250 МГц		
R55 R56	KSR2105	SAMS	Dpnp	V _{CB0} *50B; I _C *100 MA; P _D *200 MBT; h ₂₁ >30; f _T >250 MFц	SOT23,SOD23	Chicano.
	KSR2106	SAMS	Dpnp	V _{CB0} =50B; I _C =100 мA; P _D =200 мВт; h ₂₁ >68; f _T >250 МГц	SOT23,SOD23	0.0000000000
R57	KSR2107	SAMS	Dpnp	V _{CB0} =50B; I _C =100 мA; P _D =200 мBτ; h ₂₁ >68; f _T >250MΓц	SOT23,SOD23	2007/2009/2
R58	KSR2108	SAMS	Dpnp	V _{CB0} =50B; I _C =100 mA; P _D =200 mBT; h ₂₁ >56; f _T >250 MFц	SOT23,SOD23	S 55 50
R59	KSR2109	SAMS	pnp	V _{CB0} =40B; I _C =100 mA; P _D =200 mBT; h ₂₁ =100600; f _T >250 MFu	SOT23,SOD23	
R6	BZX84C7V5T	DIODS	dz	V _Z (I _{ZT} =5mA)=7.07.9B;Z _{Z1} (I _{ZT} =5mA)<150m	SOT523	A·n.c.·K
R60	KSR2110	SAMS	pnp	V _{CB0} =40B; I _C =100 mA; P _D =200 mBτ; h ₂₁ =100600; f _T >250 MΓu	S0T23,S0D23	
R61	KSR2111	SAMS	pnp	V _{CB0} =40B; I _C =100 мА; Р _D =200 мВт; h ₂₁ =100600; f ₇ > 250 МГц	S0T23,S0D23	
R62	2SC3663	NEC	npn	V _{CB0} =15B;I _C =5мA;P _D =50мВт;h ₂₁ =50250;f _T =4ГГц	S0T23,S0D23	20.000.00
R62	KSR2112	SAMS	pnp	V_{CB0} =40B; I_C =100 mA; P_D =200 mBt; h_{21} =100600; f_T >250 M Γ_{IJ}	SOT23,SOD23	
R63	KSR2113	SAMS	pnp	V_{CB0} =50 B; I_C =100 mA; P_D =300 mBT; h_{21} >68; f_T >250 M Γ_U	S0T23,S0D23	
R64	KSR2114	SAMS	pnp	V_{CB0} =50B; I_C =100 mA; P_D =300 mBT; h_{21} >68; f_T >250M Γ U,	S0T23,S0D23	
R65	SSTA65	ROHM	pnip	V _{CB0} =30 B; I _C =300 мА; h ₂₁ >50000; f _T >100 МГц	S0T23,S0D23	
R67	BFQ67R	VIS	npn	V _{CB0} =20B; I _C =50 мA; P _D =200 мВт; h ₂₁ >65; f _T =8 ГГц	S0T23,S0D23	
R6A	2SC4187	NEC	npn	V _{CB0} =15B; I _C =5 MA; P _D =50 MBT; h ₂₁ =50100; f _T =4 FF _U	SOT323,SC70	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
R6B	2SC4187	NEC	npn	V _{CR0} =15 B; I _C =5 MA; P _D =50 MBT; h ₂₁ =80160; f _T =4 FFU	SOT323,SC70	B-E-C
R6C	2SC4187	NEC	npn	V _{свп} =15 B; I _с =5 мA; P _п =50 мВт; h ₂₁ =125250; f _T =4 ГГц	SOT323,SC70	B·E·C
R7	BFR106	PHIL	npn	V _{сво} =20 B; I _C =100 мА; P _D =700 мВт; h ₂₁ =25250; f _T =5000 МГц	SOT23,SOD23	B-E-C
R7	BZX84C8V2T	DIODS	dz	V ₂ (I _{2T} =5mA)=7.78.9B;Z _{2T} (I _{2T} =5mA)<15.0m	SOT523	A·n.c.·K
R7s	BFR106	SIEM	npn	V _{сво} =20 B; I _C = 100 мА; P _D =700 мВт; h ₂₁ =25250; f _T =5000 МГц	SOT23,SOD23	B-E-C
R8	BZX84C9V1T	DIODS	dz	V ₂ (I _{2T} =5mA)=8.59.6B;Z _{2T} (I _{2T} =5mA)<15 Om	SOT523	A·n.c.·K
R9	1SS392	TOSH	shd×2	V _B >40 B; V _E (I _E =100 mA) < 0.6 B; I _E (V _B =40 B) < 5 mkA; C _T < 25 nΦ	SOT346,SC59	A1-A2-K1,K2
R9	1SS393	TOSH	shd×2	V _B < 40 B; I _E < 100 мА; V _E (I _E = 100 мА) < 0.6 B; C _D = 18 пФ	SOT323,SC70	A1-A2-K1,K2
R9	BZX84C10T	DIODS	dz	V ₂ (I _{2T} =5mA)=9.410.6B;Z _{2T} (I _{2T} =5mA)<20.0m	SOT523	A·n.c.·K
R93	SSTTIS93	ROHM	pnp	V _{GB0} =40 B; I _G =800 mA; h ₂₁ =100300; f _T >50 MFu	SOT346,SC59	B-E-C
R97	SSTIS97	ROHM	npn	V _{GB0} =40 B; I _G =500 mA; h ₂₁ =250800	SOT23,SOD23	B-E-C
R97	SSTTIS97	ROHM	npn	V _{GB0} =60 B; I _G =200 мА; h ₂₁ =250700	SOT23,SOD23	B·E·C
RA	RN2421	TOSH	Dpnp	V _{CED} =50 B; I _C =800 мA; P _D =200 мВт; f _T >250 МГц; R ₁ /R ₂ =1/1 кОм	SOT346,SC59	B·E·C
RA4	BAV70	VISH	di×2	V _B =100B;I _F =300 mA;P _D =350 mBT; I _{BB} <6 mc	SOT23,SOD23	A1-A2-K1,K2
RA6	BAS16	VISH	shd	V _B = 100 B; I _F =500 mA; P _D =350 mBT; t _{BB} < 4 HC	SOT23,SOD23	A·n.c.·K
RA7	BAV99	VISH	di×2	V _B = 100 B; I _F =300 мA; P _D =350 мВт; t _{BB} <6 нс	SOT23,SOD23	A1-K2-K1,A2
RA7	BAV99	ROHM	di×2	V _B <75 B; I _E <450 mA; V _F (I _E =150 mA)<1.25 B; I _B <2.5 mkA; t _{PB} <4 hc	SOT23,SOD23	A1-K2-K1,A2
RAA	ADR510ART	AD	vref	I _{IN} =0.110 mA;V _{DUT} =1B	SOT23,SOD23	V+·V-·TRIM/n.c
RAB	MMBD4448	VISH	shd	V _B = 100 B; I _E =500 mA; P _D =350 mBT; t _{BP} <4 HC	SOT23,SOD23	A·n.c.·K
RAF	SSTA29	ROHM	npn	V _{сво} =100 B; I _C =500 мА; h ₂₁ > 10000; f _T > 125 МГц	SOT23,SOD23	B-E-C
RAs	BFQ81	SIEM	npn	V _{CB0} =25 B; I _C =30 мА; P _D =280 мВт; h ₂₁ =50200; f _T =5800 МГц	SOT23,SOD23	B-E-C
RAT	MMSTA28	ROHM	dnpn	V _{GB0} =80 B; I _G =500 мА; h ₂₁ > 10000; f _T > 125 МГц	SOT23,SOD23	B•E•C
RAT	MMSTA28	ROHM	dnpn	V _{CR0} =80 B; I _C =500 мА; h ₂₁ > 10000; f ₁ > 125 МГц	SOT346,SC59	B·E·C
RAT	SSTA28	ROHM	non	V _{CB0} =80 B; I _C =500 мА; h ₂₁ > 10000; f _T > 125 МГц	SOT23,SOD23	B-E-C
RAV	BAS16	VISH	shd	V _B =100B;I _F =500 mA;P _B =350 mBr; t _{BB} <4 Hc	SOT23,SOD23	A·n.c.·K
RB	BZX84C2V4T	DIODS	dz	$V_{Z}(I_{ZT}=5.0 \text{ MA})=2.22.6 \text{ B; }I_{L}(V_{B}=1.0 \text{ B}) \le 50 \text{ MKA; }Z_{Z}(I_{ZT}=5.0 \text{ MA}) \le 100 \text{ OM; }I_{ZM}=200 \text{ MA}$	SOT523	A·n.c.·K
RB	MSC1621	MOT	npn	V _{CB0} =20 B; f _T =200 МГц	SOT23,SOD23	B·E·C
RB	RN2422	TOSH	Dpnp	V _{CED} =50 B; I _C =800 мА, P _D =200 мВт; f _T >250 МГц; R ₁ /R ₂ =2.2/2.2 кОм	SOT346,SC59	B·E·C
RBA	ADR280AKS	AD	vref	V _{IN} =2.45.5 B; I _{IN} < 16 mcA; V _{OUT} = 1.2 B	SOT323,SC70	VOUT•VIN• GND
RBA	ADR280ART	AD	vref	V _{IN} =2.45.5 B; I _{IN} < 16 mKA; V _{OUT} = 1.2 B	SOT23,SOD23	VIN-VOUT- GND
RBA	BAV99	VISH	di×2	V _R = 100 B; I _F =300 мА; Р _D =350 мВт; t _{RR} < 6 нс	SOT23,SOD23	A1-K2-K1,A2
RBQ	SST7208	ROHM	npn	V _{GB0} =60 B; I _C =100 мА; h ₂₁ > 100; f _T > 180 МГц	SOT23,SOD23	B·E·C
RBR	MMST6838	ROHM	npn	V_{CB0} =50 B; I_C =200 mA; h_{21} >200; f_T >50 MFu,	SOT346,SC59	B-E-C
RBR	SST6838	ROHM	npn	V_{CB0} =50 B; I_C =200 mA; h_{21} >100; f_T >50 MFu,	SOT23,SOD23	B-E-C
RBs	BF771	SIEM	npn	V_{CB0} =20 B; I_{C} =80 mA; P_{D} =580 mBt; h_{21} =50200; f_{T} =8000 MFu	SOT23,SOD23	B·E·C
RBs	BF771W	SIEM	npn	V _{GB0} =20 B; I _C =80 мА; P ₀ =400 мВт; h ₂₁ =50200; f _T =8000 МГц	SOT323,SC70	B-E-C
RC	2SC2618C	REN	npn	V _{GB0} =35 B; I _C =500 MA; P _D =150 MBT; h ₂₁ =100200	SOT23,SOD23	B-E-C
RC	BZX84C2V7T	DIODS	dz	V _Z (I _{ZT} =5mA)=2.512.89B; Z _{ZT} (I _{ZT} =5mA)<100 Om	SOT523	A·n.c.·K
RC	RN2423	TOSH	Dpnp	V_{CE0} = 50 B; I_C = 800 mA; P_0 = 200 mBt; f_1 > 250 MFu; R_1/R_2 =4.7/4.7 kOm	SOT346,SC59	B·E·C
RCs	BFR193	SIEM	npn	V _{CB0} =20 B; I _C =80 мА; P ₀ =580 мВт; h ₂₁ =50200; f _T =8000 МГц	SOT23,SOD23	B·E·C
RCs	BFR193T	SIEM	npn	V _{CB0} =20 B; I _C =80 mA; P _D =580 mBT; h ₂₁ =50200; f _T =8000 MFu	SOT416,SC75A	B·E·C
RCs	BFR193W	SIEM	npn	V _{CB0} =20 B; I _C =80 мА; P _D =580 мВт; h ₂₁ =50200; f _T =8000 МГц	SOT323,SC70	B·E·C
RD	2SC2618D	REN	npn	V _{GB0} =35 B; I _C =500 mA; P _D =150 mBT; h ₂₁ =160320	SOT23,SOD23	B-E-C
RD	BZX84C3V0T	DIODS	dz	V _Z (I _{ZT} =5.0 mA)=2.83.2B; Z _{ZT} (I _{ZT} =5.0 mA)<100 Om	SOT523	A·n.c.·K
RD	RN2424	TOSH	Dpnp	V _{CEO} =50 B; I _C =800 mA; P _D =200 mBt; f _T >250 MFu; R ₁ /R ₂ =10/10 kOm	SOT346,SC59	B·E·C
RDs	BFR180	SIEM	npn	V _{GB0} =10 B; I _G =4 мA; P _D =30 мВт; h ₂₁ =30200; I _T =6200 МГц	SOT23,SOD23	
RDs	BFR180W	SIEM	npn	V _{GB0} =10 B; I _G =4 мA; P _D =30 мВт; h ₂₁ =30200; f _T =7000 МГц	SOT323,SC70	
RE	2SA1514KE	ROHM	pnp	V _{CR0} =120 B; I _C =50 mA; P _D =200 mBT; h ₂₁ =390820; f _T >140 MFu	SOT346,SC59	
RE	2SA1579E	ROHM	pnp	V _{CB0} =120 B; I _C =50 мА; P _D =200 мВт; h ₂₁ =390820; f ₁ >140 МГц	SOT323,SC70	





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
RE	BZX84C2V4T	DIODS	dz	$V_Z(I_{ZT}=5.0 \text{ mA})=2.22.6 \text{ B}; I_L(V_R=1.0 \text{ B}) \le 50 \text{ m/A}; Z_{ZT}(I_{ZT}=5.0 \text{ mA}) \le 100 \text{ Om}; I_{ZM}=200 \text{ mA}$	SOT523	A•n.c.•K
RE	RN2425	TOSH	Dpnp	V_{CE0} = 50 B; I_C = 800 mA; P_D = 200 mBT; f_T > 250 MFu; R_1/R_2 = 0.47/10 kOm	SOT346,SC59	B·E·C
REs	BFR280	SIEM	npn	V _{CB0} =10B; I _C =10мA; P _D =80мBт; h ₂₁ =30200; f _T =7500 МГц	SOT23,SOD23	B·E·C
REs	BFR280W	SIEM	npn	V _{CB0} =10B; I _C =10 мA; P _D =80 мВт; h ₂₁ =30200; f _T =7500 МГц	SOT323,SC70	B·E·C
REs	BFR280W	SIEM	npn	V _{CB0} =10B; I _C =10 мA; P _D =80 мВт; h ₂₁ =30200; f _T =7500 МГц	SOT323,SC70	B·E·C
RF	BFR181T	TELEF	npn	V _{свп} =20 B; I _с =20 мА; Р _п =175 мВт; h ₂₁ >50; f _т =8 ГГц	SOT23,SOD23	B·E·C
RF	BZX84C3V6T	DIODS	dz	V ₂ (I ₂₇ =5 mA)=3.43.8B;Z ₂₇ (I ₂₇ =5 mA)<950m	SOT23,SOD23	A·n.c.·K
RF	RN2426	TOSH	Dpnp	V _{CEO} * 50 B; I _C * 800 MA; P _D * 200 MBT; I _T > 250 MFu; R ₁ /R ₂ * 1/10 kOm	SOT346,SC59	B·E·C
RFQ	SST6839	ROHM	pnp	V _{CR0} =50 B; I _C =200 mA; h ₂₁ > 100; f _T > 50 MF _U	SOT23, SOD23	B·E·C
RFQ	SST6839	ROHM	pnp	V _{CR0} =50 B; I _C =200 мА; h ₂₁ > 100; f _T > 50 МГц	SOT346.SC59	B·E·C
RFs	BFR181	SIEM	non	V _{CR0} = 15B; I _C = 20 мA; P _D = 160 мВт; h ₂₁ =50200; f _T = 8000 МГц	SOT23.SOD23	B·E·C
RFs	BFR181W	SIEM	non	V _{CBO} =20B; I _C =20 мA; P _D =175 мВт; h ₂₁ =50200; f _T =8000 МГц	SOT323.SC70	SEAT ARTICLE
RG	BZX84C3V9T	DIODS	dz	V _Z (I _{ZT} =5 MA)=3.74.1B;Z _{Z1} (I _{ZT} =5 MA)<90 OM	SOT523	A·n.c.·K
RG	RN2427	TOSH	Dono	V _{CEO} *50 B; I _C *800 мА; P _O *200 мВт; f _T >250 МГц; R ₁ /R ₂ *2.2/10 кОм	SOT346,SC59	
RGs	BFR182	SIEM	non	V _{CRO} =20B; I _C =35 MA; P _D =250 MBT; h ₂₁ =50200; f ₁ =8000 MF _U	SOT23.SOD23	0.00
RGs	BFR182T	SIEM	non	V _{CBO} =20B; I _C =35 MA; P _D =250 MB; I _{D21} =50200; I _T =8000 MFų	SOT416,SC75A	
RGs	BFR182W	SIEM	non	V _{CB0} =20B, I _C =35 MA; F _D =250 MB; I ₁₂ =50200; f _T =8000 MΓц	S0T323.SC70	
RH	BZX84C4V3T	DIODS	dz	V ₇ (I ₇₇ = 5 MA) = 4.04.6 B; Z ₇₇ (I ₇₇ = 5 MA) < 90 OM	SOT523	A·n.c.·K
RHs	BFR183	SIEM	non	V _{CR0} =20B; I _C =65 MA; P _D =450 MBT; h ₂₁ =50200; f _T =8000 MFų	SOT23.SOD23	NAME OF TAXABLE PARTY.
RHs	BFR183T	SIEM	1900			
	10.000000000000000000000000000000000000		npn	V _{CBO} =20B; I _C =65 мA; P _D =450 мВт; h ₂₁ =50200; f ₁ =8000МГц	SOT416,SC75A	10000
RHs	BFR183W	SIEM	npn	V _{CB0} =20 B; I _C =65 мA; P _D =450 мВт; h ₂₁ =50200; f _T =8000 МГц	S0T323,SC70	0.00.00
RJ	MCP101T-270/TT	MCHIP	mrc	V _{TR} =2.625 B; V ₀₀ =15.5 B; I ₀₀ < 60 мкA	SOT23,SOD23	
RK	MCP101T-300/TT	_	mrc	V _{TR} =2.925 B; V _{DD} =15.5 B; I _{DD} < 60 mkA	SOT23,SOD23	
RKs	BFR194	SIEM	pnp	V _{CB0} =20 B; I _C =100 мA; P _D =700 мВт; h ₂₁ =20150; f ₁ =5000 МГц	SOT23,SOD23	
RKS	RK7002A	ROHM	nMOS	V _{DS} =60B;I _D =300 мA; P _D =200 мBт; R _{DS(on)} <1.50 м	SOT23,SOD23	
RL	MCP101T-315/TT		mrc	V _{TR} =3.075 B; V _{DD} =15.5 B; I _{DD} < 60 mKA	SOT23,SOD23	
RM	MCP101T-450/TT	200000	mrc	V _{TR} =4.375 B; V _{DD} =15.5B; I _{DD} < 60 мкА	SOT23,SOD23	
RN	MCP101T-460/TT		mrc	V _{TR} =4.475 B; V _{DD} =15.5 B; I _{DD} < 60 mkA	SOT23,SOD23	
RP	MCP101T-485/TT		mrc	V _{TR} =4.725 B; V _{0D} =15.5 B; I _{OD} < 60 мкA	SOT23,SOD23	
RR	2SA1514KR	ROHM	pnip	V _{CBO} = 120 B; I _C =50 мА; P _D =200 мВт; h ₂₁ =180390; f _T > 140 МГц	SOT346,SC59	
RR	2SA1579R	ROHM	pnp	V_{CB0} = 120 B; I_C = 50 mA; P_0 = 200 mBt; h_{21} = 180390; f_7 > 140 M Γ_{II}	SOT323,SC70	
RRA	BC847AF	AUK	npn	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBT; h_{21} =110220; f_T =150 M Γ LL	SOT490,SC89	10000000000
RRB	BC847BF	AUK	npn	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ =200450; f _T =150 MF _U	SOT490,SC89	72.71.72
RRC	BC847CF	AUK	npn	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBt; h_{21} =420800; f_T = 150 MFц	SOT490,SC89	B·E·C
RS	2SA1514KS	ROHM	pnp	V_{C80} = 120 B; I_C = 50 mA; P_D = 200 mBT; h_{21} = 270560; f_T > 140 MFu,	SOT346,SC59	B·E·C
RS	2SA1579S	ROHM	pnp	V_{C80} = 120 B; I_C =50 mA; P_0 = 200 mBT; h_{21} = 270560; f_T > 140 M Γ_{U_L}	SOT323,SC70	B·E·C
RSR	SST5210	ROHM	npn	V_{CB0} =50B; I_C =200 mA; h_{21} =200600; f_T >30 M Γ_{IJ}	SOT23,SOD23	B·E·C
RT3	2SC4400	SANYO	npn	V_{CB0} =40B; I_C =50 MA; P_D =150 MBT; h_{21} =60120; f_T >750 MFL,	SOT323,SC70	B·E·C
RT4	2SC4400	SANYO	npn	V_{CB0} =40B; I_C =50 MA; P_D =150 MBT; h_{21} =90180; f_T >750 MFL	SOT323,SC70	B·E·C
RT5	2SC4400	SANYO	npn	V _{CB0} =40B; I _C =50 мA; P _D =150 мВт; h ₂₁ =135270; f _T >750 МГц	SOT323,SC70	B·E·C
RVX	MMST918	ROHM	npn	V_{CB0} = 30 B; I_C = 50 MA; h_{21} > 20650; f_T =600 M Γ_{IJ}	SOT346,SC59	B·E·C
RVZ	MMST4126	ROHM	pnp	V _{CB0} =25B; I _C =200 мА; h ₂₁ =120360; f _T >250 МГц	SOT23,SOD23	B·E·C
RVZ	MMST4126	ROHM	pnp	V _{сво} = 25 B; I _c = 200 мА; h ₂₁ = 120360; f _T > 250 МГц	S0T346,SC59	B·E·C
RX7	SST6426	ROHM	non	V _{CR0} =40 B; I _C =500 mA; h ₂₁ =300300000	SOT23,SOD23	B·E·C
RZC	MMST4124	ROHM	non	V _{CR0} =30 B; I _C =200 мА; h ₂₁ =120360; f _T >300 МГц	SOT346,SC59	
RZC	SST4124	ROHM	non	V _{CB0} =30B, I _C =200 MA; h ₂₁ =120360; f _T >300 MF _U	SOT23.SOD23	22.000
RZQ	MMST7157	ROHM	onp	V _{CB0} =60 B; I _C =200 mA; h ₂₁ >100	SOT23,SOD23	
SO SO	HSMP3880	HP	pinp	V _{CBO} -00B, iC-200 мВ, 1912 100 I _E <1A; P _D <250 мВт; V _{BB} >100 В; R _S <6.50м; СТ<0.40 пФ	SOT23,GOD23	
S0	SST270	SIL	pFET	V _{DS} =30B;P _D =350MBT;Q _F =6MCM;I _{DSS} =215MA	SOT23,SOD23	
	uu1210	OIL	http:/	00 00	-	
S1	BBY31	PHIL	var	$V_R < 30 B; I_F < 20 \text{ mA}; I_R < 10 \text{ HA}; R_S < 1.20 \text{ m}; C_{1B} = 16.5 \text{ n} \Phi; C_{28B} = 1.62 \text{ n} \Phi$	SOT23.SOD23	

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
S1	SST271	SIL	pFET	V _{DS} =30B;P _D =350мBт;I _{DSS} =650мA; g _F =0.5мСм	SOT23,SOD23	D·S·G
S12	BBY39	PHIL	var×2	V _R <30 B; I _F <20 мА; С _{1 B} =16.5 пФ; С _{28 B} =1.62 пФ	SOT23,SOD23	A1+A2+K1,K2
S13	BBY42	PHIL	var	$V_R < 30 \text{ B}, I_F < 20 \text{ mA}; I_R < 10 \text{ HA}; R_S < 10 \text{ m}; C_{18} > 31 \text{ n}\Phi; C_{288} = 2.43 \text{ n}\Phi$	SOT23,SOD23	A·n.c.·K
S14	BB901	PHIL	ASL	$V_B \le 28 B; I_F \le 20 \text{ MA}; I_B \le 10 \text{ HA}; R_S \le 30 \text{M}; C_{28 B} \le 1.055 \text{ n}\Phi; C_{0.5 B}/C_{28 B} \ge 12$	SOT23,SOD23	A·n.c.·K
S14	SST5114	SIL	pFET	V _{DS} =30B;P _D =350мВт;I _{DSS} =3090мА;R _{DS(on)} <75Ом	SOT23,SOD23	D·S·G
S15	SST5115	SIL	pFET	V _{DS} =30B;P _D =350 MBT;I _{DSS} =1560 MA;R _{DS(on)} <100 OM	SOT23,SOD23	D·S·G
S16	SST5116	SIL	pFET	V _{DS} =30 B; P _D =350 мВт; I _{DSS} =525 мА; R _{DS(on)} < 150 Ом	SOT23,SOD23	D·S·G
S16	ZHCS1006	ZETEX	shd	V _B < 60 B; I _F < 0.9 A; V _F (I _F = 1 A) < 0.6 B; I _B < 100 m; A; C _D < 17 nΦ; t _{BB} < 12 hc	SOT23,SOD23	A·n.c.·K
s1A	SMBT3904	SIEM	npn	V_{CB0} =60 B; I_C =200 mA; P_D =330 mBr; h_{21} =100300; f_T >300 MFu	SOT23,SOD23	B-E-C
s1B	PXTA93	SIEM	pnp	V _{GB0} =200 B; I _G =500 мА; P _D =1000 мВт; h ₂₁ >40; f _T >50 МГц	SOT23,SOD23	B-E-C
s1B	SMBT2222	SIEM	npn	V _{GB0} =60 B; I _G =600 мА; P _D =330 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	B-E-C
s1C	SMBTA20	SIEM	npn	V _{GB0} =40 B; I _G = 100 мА; P ₀ =330 мВт; h ₂₁ =40400; f _T > 125 МГц	SOT23,SOD23	B·E·C
s1D	SMBTA42	SIEM	npn	V _{сво} =300 B; I _c =500 мА; P _D =360 мВт; h ₂₁ >40; f _T >50 МГц	SOT23,SOD23	B-E-C
s1E	SMBTA43	SIEM	non	V _{CB0} =200 B; I _C =500 mA; P _D =360 mBr; h ₂₁ >40; f _T >50 MF _U	SOT23.SOD23	B-E-C
sIG	SMBTA06	SIEM	non	V _{GB0} =80 B; I _C =500 мА; P _D =330 мВт; h ₂₁ >100; f _T >100 МГц	SOT23,SOD23	B-E-C
s1H	SMBTA05	SIEM	ngn	V _{GB0} =60 B; I _G =500 мА; P _D =330 мВт; h ₂₁ >100; f _T =100 МГц	SOT23,SOD23	
s1K	SMBT6428	SIEM	non	V _{CPD} =60 B; I _C =200 мА; P _D =330 мВт; h ₂₁ =250650; f _T =200 МГц	SOT23,SOD23	
s1L	SMBT6429	SIEM	non	V _{GB0} =55 B; I _G =200 мА; P _D =330 мВт; h ₂₁ =5001250; f _T =200 МГц	SOT23,SOD23	
sIM	SMBTA13	SIEM	npn	V _{GB0} =30 B; I _C =300 мА; P _D =330 мВт; h ₂₁ >5000; f _T >125 МГц	SOT23,SOD23	1070534720
sIN	SMBTA14	SIEM	non	V _{CR0} =30 B; I _C =300 мА; Р _П =330 мВт; I _{P2} =>10000; f _T >125 МГц	SOT23,SOD23	1150 110 110
s1P	SMBT2222A	SIEM	non	V _{CB0} =75 B; I _C =600 мA; P _D =330 мBт; h _{P1} =100300; f _T >300 МГц	SOT23,SOD23	3222 28
stV	SMBT6427	SIEM	npn	V _{CB0} =40 B; I _C =500 mA; P _D =360 mBT; h ₂₁ =20000200000; f _T >130 MFu	SOT23,SOD23	
S2	BBY40	PHIL	var	$V_B \le 30 \text{ B}; I_F \le 20 \text{ MA}; I_B \le 10 \text{ HA}; R_S \le 0.7 \text{ OM}; C_{3B} = 2632 \text{ n}\Phi; C_{25B} = 4.36 \text{ n}\Phi$		
S2	BFQ31	ZETEX	npn	V _{CB0} =30 B; I _C =100 mA; P _D =330 mBT; h ₂₁ >20; f _T >600 MFu	SOT23,SOD23	
S2	KTA2014	KEC	onp	V _{CB0} =50 B; I _C =150 MA; P _D =100 MBT; h ₂₁ =70140; f _T >80 MFu	SOT323,SC70	-50.00000
s2A	SMBT3906	SIEM	ono	V _{CB0} =40 B; I _C =200 mA; P _D =330 mBT; h ₂₁ =100300; f _T >250 MF _U	SOT23.SOD23	100000000
s2B	SMBT2907	SIEM	ono	V _{CB0} =40 B; I _C =600 MA; P _D =330 MBT; h ₂₁ =100300; f _T >200 MF _U	SOT23,SOD23	T00E 0
s2C	SMBTA70	SIEM	gng	V _{CBI} =40 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =40400; f _T >125 МГц	SOT23,SOD23	
s2D	SMBTA92	SIEM	pnp	V _{DBD} =300 B; I _C =500 мА; P _D =360 мВт; h ₂₁ > 25; f _T >50 МГц	SOT23,SOD23	
s2E	SMBTA93	SIEM	onp	V _{DB0} =300 B; I _C =300 мВ, P _D =360 мВт; N ₂₁ > 25; f _T > 50 МГц	SOT23,SOD23	200000000000000000000000000000000000000
s2F	SMBT2907A	SIEM	pnp	V _{CB0} =200 B; I _C =500 MA; P _D =300 MB; I _{N2} =20, I _T >30 MIQ V _{CB0} =60 B; I _C =600 MA; P _D =330 MB; I _{N2} =100300; I _T >200 MIQ	SOT23,SOD23	100000000
s2G	SMBTA56	SIEM	ono	V _{CB0} -50 B; I _C =500 MA; P _D =330 MB; h ₂₁ =100300, f _T =200 MFц	SOT23,30D23	1000000000
s2H	SMBTA55	SIEM	P. P.	V _{CBO} =60 B; I _C =500 MA; P _D =330 MB; I _{Pd} =100; I _T =100 MI[q]	SOT23,30D23	TOTAL CO.
s2P	SMBT5086	SIEM	pnp	000 0 0 0	SOT23,SOD23	
s2P s2Q	SMBT5087	SIEM	pnp	V _{CB0} =50 B;I _C =50 MA; P _D =330 MBT; h ₂₁ =150500; f _T >40 MFi _L	SOT23,SOD23	/
s2U s2U		-	pnp	V _{CB0} =50 B; I _C =50 мA; P _D =330 мBт; h ₂₁ =250800; f _T >40 MFц	SOT23,SOD23	
s2V	SMBTA63	SIEM	pnp	V _{CB0} =30 B; I _C =500 mA; P _D =360 mBr; h ₂₁ >5000; f _T >125 MFu		Sa taras and
	SMBTA64	SIEM	pnp	V _{CB0} =30 B; I _C =500 MA; P _D =360 MBT; h ₂₁ >10000; f _T >125 MFU	SOT23,SOD23	
S3	BBY51	SIEM	var×2	V _R <7 B; I _F <20 mA; I _R <0.01 mrA; C _{1 B} =4.56.1 πΦ; C _{1 B} /C _{4 B} =1.552.2	SOT23,SOD23	No. 2010 100 100 100 100 100 100 100 100 10
S3	BFQ31R	ZETEX	npn	V _{GB0} =30 B; I _C =100 мА; P _D =330 мВт; h ₂₁ >20; f _T >600 МГц	SOT23,SOD23	2000
S3s	BBY51	INF	var×2	V _R <7 B; IF<20 мA; I _R <0.01 мкА; С _{1 В} =5.055.75 пФ; С _{4 В} =2.53.7 пФ	SOT23,SOD23	
S4	BFQ31A	ZETEX	npn	V _{GB0} =30 B; I _C =100 мА; P _D =330 мВт; h ₂₁ >100; f _T >600 МГц	SOT23,SOD23	
S4	KTA2014	KEC	pnp	V _{GB0} =50 B; I _G =150 мA; P _D =100 мВт; h ₂₁ =120240; f _T >80 МГц	SOT323,SC70	
S4	SST174	SIL	pFET	V _{DS} =30 B; P _D =350 MBr; I _{DSS} =20135 MA; R _{DS(cn)} < 85 OM	SOT23,SOD23	
S5	BFQ31AR	ZETEX	npn	V_{GB0} =30 B; I_C =100 mA; P_D =330 mBT; h_{21} >100; f_T >600 MF $_{LL}$	SOT23,SOD23	1,330-933-034
S5	SST175	SIL	pFET	V _{DS} =30 B; P _D =350 мВт; I _{DSS} =770 мА; R _{DS(on)} <125 Ом	SOT23,SOD23	70.00
S50	BS850	GS	pFET	V _{DSS} =60 B;I _D =250 mA;P _D =310 mBT; V _{GS} <20 B	SOT23,SOD23	1,000
s56	ZHCS506	ZETEX	shd	$V_R \le 60 \text{ B}; I_F \le 0.5 \text{ A}; V_F (I_F = 0.5 \text{ A}) \le 0.63 \text{ B}; I_R \le 40 \text{ m/s}, C_0 \le 20 \text{ n}\Phi; I_{RR} \le 10 \text{ Hz}$	SOT23,SOD23	
s5A	SMBD6050	SIEM	di	V_B <70 B; I_F <250 mA; V_F (I_F =100 mA)<1.1 B; I_B <0.1 mrA; C_D <2.5 n Φ ; t_{BB} <10 Hc	SOT23,SOD23	
s5B	SMBD6100	SIEM	di×2	V_B < 70 B; I_F < 250 mA; V_F (I_F = 100 mA) < 1.1 B; I_B < 0.1 mrA; C_0 < 2.5 πΦ; I_{BH} < 15 HC	SOT23,SOD23	A1 • A2 • K1, K2





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
s5C	SMBD7000	SIEM	di×2	$V_R \le 100 B_1 I_F \le 200 \text{mA}; V_F (I_F = 100 \text{mA}) \le 1.1 B_1 I_R \le 0.5 \text{mkA}; C_0 \le 2.0 \text{n} \Phi; t_{BB} \le 15 \text{Hz}$	SOT23,SOD23	A1•K2•K1,A2
s5D	SMBD914	SIEM	di	V_R < 70 B; I_F < 250 mA; V_R (I_F = 100 mA) < 1.0 B; I_R < 0.025 mkA; C_0 < 2.0 n Φ ; I_{RR} < 4 HC	SOT23,SOD23	A•n.c.•K
S5s	BAT15-05W	INF	shd	V _B <4B; I _E <110 мA; V _E (I _E =10 мA)<0.41B; С _D <0.35 пФ	S0T323,SC70	A1+A2+K1,K2
S5s	BBY52	SIEM	var×2	V _B <7B; I _E <20mA; I _B <0.01 mκA; C _{1B} =1.12.5 nΦ; C _{1B} /C _{4B} =1.12.1	SOT23,SOD23	A1-A2-K1,K2
S6	KTA2014	KEC	pnp	V _{CPD} =50 B; I _C =150 мА; Р _D =100 мВт; h ₂₁ =200400; f _T >80 МГц	SOT323,SC70	B·E·C
S6	SST176	SIL	pFET	V _{DS} =30 B; P _D =350 MBr; I _{DSS} =235 MA; R _{DS(op)} < 250 OM	SOT23,SOD23	D·S·G
S6p	BF510	PHIL	nFET	V _{DS} =20 B;I _{DS} <3 mA; P _D =250 mBT; g _F =2.5 mc	SOT23,SOD23	G·D·S
S7	SST177	SIL	pFET	V _{DS} =30 B; P _D =350 мВт; I _{DSS} =1.520 мА; R _{DS(on)} < 300 Ом	SOT23,SOD23	D·S·G
S70	BS870	GS	nFET	V _{DSS} =60B; I _D =250 mA; P _D =310 mBt; V _{GS} < 20 B	SOT23,SOD23	G·S·D
S72	2N7002	VISH	nFET	V _{DS} =60B;I _D =115мA;P _D =200мВт;V _{GS} <2.5B;C _{ECC} =60пФ	SOT23,SOD23	G·S·D
S76	ZHCS756	ZETEX	shd	$V_R < 60B$; $I_E < 0.75A$; $V_E (I_E = 0.75A) < 0.61B$; $I_R < 100$ m/kA; $C_D < 17$ n/b; $I_{BB} < 12$ Hz	SOT23,SOD23	A•n.c.•K
S7p	BF511	PHIL	nFET	V _{DS} =20 B;I _{DS} <7 mA; P _D =250 mBT; g _F =4 mc	SOT23,SOD23	G·D·S
S7s	BBY53	INF	var×2	V _B <6B; I _E <20мA; I _B <0.01 мкА; С _{1 B} =4.85.8 пФ; С _{3 B} =1.853.1 пФ	SOT23,SOD23	A1+A2+K1,K2
S7s	BBY53-05W	INF	var	V _R <6B; I _E <20мA; I _R <0.01 мкА; С _{1 В} =4.85.8 пФ; С _{3 В} =1.853.1 пФ	SOT323,SC70	A1 · A2 · K1, K2
S8	BAT1504	SIEM	shd	V _R <4B; I _E <110 мA; V _E (I _E =10 мA)<0.48B; C _D <0.35 пФ	SOT23,SOD23	A·n.c.·K
S8p	BF512	PHIL	nFET	V _{DS} =20 B; I _{DS} < 12 mA; P _D =250 mB⊤; g _F =6 mc	SOT23,SOD23	G·D·S
S8s	BAT15-04W	INF	shd	V _B <4B; I _F <110 mA; V _F (I _F =10 mA)<0.41B; C _D <0.35 nΦ	S0T323,SC70	A1-K2-K1,A2
S9	1SS394	TOSH	shd	V _B >10B; V _E (I _E =100 mA)<0.5B; I _E (V _B =10B)<20 mκA; C _T <40 nΦ	SOT346,SC59	A+n.c.+K
S9	1SS395	TOSH	shd	V _B <10B; I _E <100 mA; V _E (I _E =100 mA)<0.5B; C _D <40 nΦ	SOT323,SC70	A·n.c.·K
S9p	BF513	PHIL	nFET	V _{DS} =20 B;I _{DS} <18 mA;P _D =250 mB _T ; g _F =7 mc	SOT23,SOD23	G·D·S
SA	BSS123	ZETEX	nMOS	V _{DS} =100 B; I _D =170 mA; P _D =330 mBT; G _F =90 mCm; R _{DS(on)} =14 Om	SOT23,SOD23	G·S·D
sA2	SMBD2836	SIEM	di×2	$V_B \le 50 B$; $I_E \le 200 mA$; $V_E (I_E = 100 mA) \le 1.2 B$; $I_B \le 0.1 m kA$; $C_D \le 4 \pi \Phi$; $t_{BB} \le 6 H c$	SOT23,SOD23	K1-K2-A1,A2
sA3	SMBD2835	SIEM	di×2	$V_R \le 30 B$; $I_F \le 200 mA$; $V_R (I_F = 100 mA) \le 1.2 B$; $I_R \le 0.1 meA$; $C_D \le 4 \pi \Phi$; $t_{RR} \le 6 mc$	SOT23,SOD23	K1-K2-A1,A2
sA4	SMBD2838	SIEM	di×2	V _R <50 B; I _F <200 mA; V _F (I _F =100 mA)<1.2 B; I _R <0.1 mrA; C _D <4 nΦ; t _{RR} <6 HC	SOT23,SOD23	A1-A2-K1,K2
sA5	SMBD2837	SIEM	di×2	$V_R \le 30 B$; $I_F \le 200 \text{ mA}$; $V_F (I_F = 100 \text{ mA}) \le 1.2 B$; $I_R \le 0.1 \text{ m/A}$; $C_D \le 4 \text{ n}\Phi$; $t_{RR} \le 6 \text{ n}C$	SOT23,SOD23	A1-A2-K1,K2
SAs	BSS123	INF	nMOS	V _{DS} =100 B; I _D =170 мA; P _D =360 мВт; g _F =170 мСм; R _{DS(on)} <60 м	SOT23,SOD23	G·S·D
SB	2SA1121B	REN	pnp	V _{CB0} =35B; I _C =500 mA; P _D =150 mBt; h ₂₁ =60120	SOT23,SOD23	B·E·C
SBp	BB200	PHIL	var×2	$V_R > 18B; I_R (V_R = 10B) < 0.05 \text{ mkA}; C_{1B} = 65.874.2 n\Phi; C_{4.5B} C_{4.5B} = 1214.8 n\Phi$	SOT23,SOD23	A1+A2+K1,K2
SBs	BSS145	INF	nMOS	V _{DS} =65B; I _D =220 MA; P _D =360 MBT; Q _E >120 MCM; R _{DS(cn)} =3.5 OM	SOT23,SOD23	G·S·D
SC	2SA1121C	REN	pnp	V _{CB0} =35B; I _C =500 mA; P _D =150 mBr; h ₂₁ =100200	SOT23,SOD23	B·E·C
sC3	SMBT4126	SIEM	pnp	V_{CB0} = 25 B; I_C = 200 mA; P_D = 330 mBT; h_{21} = 120360; f_T > 300 MF $_{II}$	SOT23,SOD23	B·E·C
SCp	BB201	PHIL	var×2	V _B >15B; I _B (V _B =15B)<0.2 мкА; С _{1 B} =89102 пФ; С _{7.5 B} =25.529.7 пФ	SOT23,SOD23	A1+A2+K1,K2
SD	2SA1121D	REN	pnp	V _{CB0} =35B; I _C =500 mA; P _D =150 mBt; h ₂₁ =160320	SOT23,SOD23	B·E·C
SDs	BSS284	INF	pMOS	V _{DS} =50 B;I _D =130 мA; P _D =360 мВт; g _F >50 мСм; R _{DS(on)} =10 Ом	SOT23,SOD23	G·S·D
SF0	BB804	PHIL	var×2	$V_R \le 18 B$; $I_R \le 50 \text{ mA}$; $I_R \le 20 \text{ mA}$; $R_S \le 0.2 \text{ Om}$; $C_{2B} = 4243.5 \text{ n}\Phi$; $C_{2B}/C_{8B} \ge 1.65$	SOT23,SOD23	A1+A2+K1,K2
SF0	BB804F0	SIEM	var×2	$V_R < 18B; I_F < 50 \text{ mA}; I_R < 0.02 \text{ mKA}; C_{2B} = 4243.5 \text{ n}\Phi; C_{2B} > 1.65$	SOT23,SOD23	A1+A2+K1,K2
SF1	BB804	PHIL	var×2	$\begin{array}{l} V_{\rm R}\!<\!18B;I_{\rm F}\!<\!50{\rm mA;I_{R}}\!<\!20{\rm HA;R_{S}}\!<\!0.2{\rm Om;C_{2B}}\!\!=\!\!4344.5{\rm n\Phi;}\\ C_{2B}/C_{BB}\!>\!1.65 \end{array}$	SOT23,SOD23	A1-A2-K1,K2
SF1	BB804F1	SIEM	var×2	$V_R \le 18 B$; $I_F \le 50 \text{ mA}$; $I_R \le 0.02 \text{ mKA}$; $C_{2B} = 4344.5 \text{ m}$; $C_{2B} / C_{8B} \ge 1.65$	SOT23,SOD23	
SF2	BB804	PHIL	var×2	$\begin{array}{l} V_{R}\!<\!18B;I_{F}\!<\!50\text{mA};I_{R}\!<\!20\text{HA};R_{S}\!<\!0.2\text{Om};C_{2B}\!^{-}\!$	SOT23,SOD23	
SF2	BB804F2	SIEM	var×2	$V_R \le 18B$; $I_F \le 50$ MA; $I_R \le 0.02$ MKA; $C_{2B} = 4445.5$ m Φ ; $C_{2B}/C_{8B} \ge 1.65$	SOT23,SOD23	Section of the sectio
SF2	BB804W	PHIL	var×2	$V_R \le 18B$; $I_F \le 50$ mA; $I_R \le 0.02$ mrA; $C_{2B} = 4246.5$ n Φ ; $C_{2B}/C_{8B} \ge 1.65$	SOT23,SOD23	
SF3	BB804	PHIL	var×2	$\begin{array}{l} V_R \!<\! 18 B_i I_F \!<\! 50 \text{mA}; I_R \!<\! 20 \text{HA}; R_S \!<\! 0.2 \text{Om}; C_{2B} \!\!=\!\! 4546.5 \text{n}\Phi; \\ C_{2B} \!/\! C_{BB} \!>\! 1.65 \end{array}$	SOT23,SOD23	A1 • A2 • K1, K2
SF3	BB804F3	SIEM	var×2	$V_R \le 18B$; $I_F \le 50$ mA; $I_R \le 0.02$ mrA; $C_{2B} = 4546.5$ n Φ ; $C_{2B}/C_{8B} \ge 1.65$	S0T23,S0D23	A1 • A2 • K1, K2
SF4	BB804F4	SIEM	var×2	$V_R \le 18B$; $I_F \le 50$ mA; $I_R \le 0.02$ mrA; $C_{2B} = 4647.5$ n Φ ; $C_{2B}/C_{8B} \ge 1.65$	SOT23,SOD23	
SF5	BB804	PHIL	var×2	$V_R \le 18B$; $I_F \le 50$ mA; $I_R \le 0.02$ mrA; $C_{2B} = 4246.5$ m Φ ; $C_{2B}/C_{8B} \ge 1.65$	SOT23,SOD23	
SG	2SA1586	TOSH	pnp	V _{CB0} =50B; I _C =150 мA; P ₀ =100 мВт; h ₂₁ =200400; f _T >80 МГц	SOT323,SC70	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
SGR	KTA2014	KEC	pnp	V _{CR0} =50 B; I _C =150 mA; P _D =100 mBt; h ₂₁ =200400; f _T >80 MFu,	SOT323,SC70	B·E·C
SH1	BB814H1	INF	var×2	V _B < 18 B; I _E < 50 mA; I _B < 0.02 mkA; C _{2B} = 4345 nΦ; C _{2B} /C _{8B} = 2.052.25	SOT23,SOD23	A1 • A2 • K1. K2
SH2	BB814H2	INF	var×2	V _B <18 B, I _E <50 мA; I _B <0.02 мкА; С _{2B} =44.546.5 пФ; С _{2B} /С _{BB} =2.052.25		-
SM	2SC3082KM	ROHM	ngn	V _{CB0} =30 B; I _C =50 mA; P _D =200 mBτ; h ₂₁ =3982; f _T >110 MΓu	SOT346.SC59	
SM	2SC4100M	ROHM	npn	V _{CR0} =30 B; I _C =50 mA; P _D =200 mBτ; h _{P1} =3982; f _T >110 MΓu	SOT323,SC70	100000000000
SM	2SC4619	ROHM	npn	V _{CR0} =30 B; I _C =50 mA; P _D =150 mBr; h ₂₁ =3982; f _T >110 MFu	SOT416,SC75A	1000000000
SMs	BB914	SIEM	var×2	V _B <18 B, I _F <50 mA, I _B <0.02 mKA; C _{2B} =42.545 nΦ; C _{2B} /C _{8B} =2.282.42	SOT23,SOD23	
SN	2SC3082KN	ROHM	ngn	V _{CR0} =30 B; I _C =50 мА; P _D =200 мВт; h ₂₁ =56120; f _T >110 МГц	SOT346.SC59	
SN	2SC4100N	ROHM	npn	V _{CR0} =30 B; I _C =50 mA; P _D =200 mBτ; h ₂₁ =56120; f _T >110 MΓu	SOT323.SC70	
SN	2SC4619	ROHM	npn	V _{CR0} =30 B; I _C =50 mA; P _D =150 mBr; h _{P1} =56120; f _T >110 MFu	SOT416,SC75A	
SO.	2SA1586	TOSH	ono	V _{CB0} =50 B; I _C =150 MA; P _D =100 MBT; h ₂₁ >70140; f _T >80 MFu	SOT323,SC70	
SO	KTA2014	KEC	ono	V _{CR0} =50 B; I _C =150 MA; P _D =100 MBT; h ₂₁ =70140; f _T >80 MFu	SOT323.SC70	17503270000
SP	2SC3082KP	ROHM	npn	V _{CB0} =30 B; I _C =50 мА; P _D =200 мВт; h ₂₁ =82180; f _T >110 МГц	SOT346,SC59	100000000000000000000000000000000000000
SP	2SC4100P	ROHM	non	V _{CB0} =30 B; I _C =50 MA; P _D =200 MBT; I _{P2} =82180; f _T >110 MFц	SOT323.SC70	1800 /A D/A
SP	2SC4619	ROHM	ngn	V _{GB0} =30 B; I _C =50 MA; P _D =150 MB; I _{P2} =82180; f _T >110 MF _U	SOT416,SC75A	
SP		_	,			
SPs	BSS84 BSS84	ZETEX	pMOS	V _{DS} *50 B; I _D *130 MA; P _D *360 MBT; Q _F *50 MCM; R _{DS(on)} *10 OM	SOT23,SOD23 SOT23,SOD23	
				V _{DS} =50 B; I _D =130 mA; P _D =360 mBr; g _F >50mCm; R _{DS[on]} <10 0 m		
SQ	2SC3082KQ	ROHM	npn	V _{CB0} =30 B; I _C =50 мA; P ₀ =200 мBr; h ₂₁ =120270; f _T >110 МГц	SOT346,SC59	T00570070
SQ	2SC4100Q	ROHM	npn	V _{CB0} =30 B; I _C =50 мА; P _O =200 мВт; h ₂₁ =120270; f _T >110 МГц	SOT323,SC70	1107 12 130
SQ	2SC4619	ROHM	npn	V _{CB0} =30 B;I _C =50 мA; P ₀ =150 мBт; h ₂₁ =120270; f _T >110 МГц	SOT416,SC75A	130000 30
SR	2SC3929R	PAN	npn	V_{CB0} =35 B; I_C =50 mA; P_D =150 mBr; h_{21} =180360; f_T =100 M Γ_{II}	SOT323,SC70	
SRs	BSS131	INF	nMOS	V _{DS} = 240 B; I _D = 100 мА; P _D = 360 мВт; g _F = 140 мСм; R _{DS(en)} = 6 Ом	SOT23,SOD23	
SS	2SC3929S	PAN	npn	V_{CB0} =35 B; I_C =50 mA; P_D =150 mBT; h_{21} =260520; f_T =100 M Γ_{II}	SOT323,SC70	
SS	BSS138	ZETEX	nMOS	V _{DS} =50 B; I _D =200 мА; P _D =360 мВт; g _F =120 мСм; R _{DS(on)} =6 Ом	SOT23,SOD23	00000
SSF	SP0610T	SIEM	pMOS	V _{DS} =60 B; I _D =130 mA; P _D =360 mBT; Q _F >80 mCm; R _{DS(on)} =10 Om	SOT23,SOD23	
sSG	SN7002	SIEM	nMOS	V _{DS} =60 B;I _D =190 MA;P _D =360 MBT;R _{DS(on)} <7.5 OM	SOT23,SOD23	200
SH	BSS119	INF	nMOS	V_{DS} = 100B; I_D = 170 mA; P_D =360 mBt; g_F > 100 mCm; $R_{DS(on)}$ = 60 m	SOT23,SOD23	
sSJ	BSS7728	SIEM	nMOS	V _{DS} =60 B; I _D =150 мА; P _D =360 мВт; g _F =80 мСм; R _{DS(on)} =7.5 Ом	SOT23,SOD23	G·S·D
SSN	SN7002N	SIEM	nMOS	V _{DS} =60 B;I _D =160 MA;P _D =360 MBT;R _{DS(00)} <7.5 OM	SOT23,SOD23	G·S·D
sSN	SN7002W	SIEM	nMOS	V _{DS} =60 B; I _D =180 mA; P _D =500 mBT; R _{DS(on)} < 7.5 Om	SOT323,SC70	G·S·D
SSs	BSS138	INF	nMOS	V_{DS} =50 B; I_D =220 mA; P_D =360 mBT; Q_F >1200 mCm; $R_{DS(on)}$ =3.5 Om	SOT23,SOD23	G·S·D
ST	2SC3929T	PAN	npn	V_{CB0} =35 B; I_C =50 mA; P_0 =150 mBt; h_{21} =360700; f_T =100 M Γ_{II}	SOT323,SC70	B·E·C
STs	BSS139	INF	nMOS	V _{DS} =250B; I _D =40 мА; P _D =360 мВт; g _F >50 мСм; R _{DS(m)} <100 Ом	SOT23,SOD23	G·S·D
SY	2SA1586	TOSH	pnp	V_{CB0} =50 B; I_C =150 mA; P_D =100 mBT; h_{21} =120240; f_T >80 MFu	SOT323,SC70	B·E·C
SY	KTA2014	KEC	pnp	V_{CB0} =50 B; I_C =150 mA; P_D =100 mBt; h_{21} =120240; f_T >80 MFu	SOT323,SC70	B·E·C
sZC	SMBT4124	SIEM	npn	V_{CB0} =30 B; I_C =200 mA; P_D =330 mBT; h_{21} =120360; f_T >300 MF $_{41}$	SOT23,SOD23	B·E·C
TO	HSMS2860	HP	shd	$V_{BR} > 5 B; V_{E}(I_{E}=30 \text{ mA}) < 0.6 B; C_{T} < 0.30 \text{ n}\Phi; R_{D}=10 \text{ 0}M$	SOT23,SOD23	A·n.c.·K
TO	HSMS286B	HP	shd	V _E (I _E =1 mA) < 0.35 B; C _T < 0.30 πΦ	SOT323,SC70	A·n.c.·K
01	PDTA143ET	PHIL	Dono	V _{GB0} =50 B; I _C =100 mA; P _D =250 mBt; h ₂₁ >30; 4.7 кOm/4.7 кOm	SOT23,SOD23	B·E·C
01	PDTA143EU	PHIL	Dono	V _{GB0} =50 B; I _C =100 mA; P _D =250 mBT; h ₂₁ >30; 4.7 кOm/4.7 кOm	SOT323,SC70	
102	PDTC143ET	PHIL	Dnpn	V _{CR0} =50 B; I _C =100 mA; P _D =250 mBT; h ₂₁ >30; 4.7 кOm/4.7 кOm	SOT23,SOD23	
02	PDTC143EU	PHIL	Dnpn	V _{GR0} =50 B; I _G =100 mA; P _D =250 mBT; h ₂₁ >30; 4.7 кOm/4.7 кOm	SOT323.SC70	
03	PDTA114ET	PHIL	Dono	V _{ORD} =50 B; I _C =100 mA; P _D =200 mBr; h ₂₁ >30; 10 kOm/10 kOm	SOT23,SOD23	
03	PDTA114EU	PHIL	Dono	V _{GB0} =50 B; I _C =100 mA; P _D =200 mBt; h ₂₁ >30; 10 kOm/10 kOm	SOT323,SC70	
04	PMSS3904	PHIL	nan	V _{CR0} =60 B; I _C =200 мА; P _D =200 мВт; h ₂₁ =100300; f _T >180 МГц	SOT323.SC70	100000000000000000000000000000000000000
05	PDTA124ET	PHIL	Dono	V _{CB0} =50 B; I _C =100 mA; P _D =250 mBt; h ₂₁ >60; 22 kOm/22 kOm	SOT23.SOD23	V8-3177 - 415
05	PDTA124EU	PHIL	Dono	V _{CR0} =50 B; I _C =100 MA; P _D =250 MBT; I _{D2} >60; 22 kOM/22 kOM	SOT323.SC70	100000
T05	SSTPAD5	CALOG		V _B =55B;I _E <10 MA;V _E (I _E =1 MA)<1.5B;I _B <5πA;C _T <2πΦ	SOT23,SOD23	
06	PDTC124EU	PHIL	Dnpn	V _{CR0} =50 B; I _C =100 mA; P _D =250 mB; h ₂₁ >60; 22 kOm/22 kOm	SOT323,SC70	
06	PMSS3906	PHIL	-	050 0 0	SOT323,SC70	
	LINGGOOD	FIL	pnp	V_{CB0} =40 B; I_C =200 mA; P_D =200 mBT; h_{21} =100300; f_T >150 MF $_{4}$	001020,0010	D-E-0
07	PDTA144ET	PHIL	Dono	V _{CB0} =50 B; I _C =100 mA; P _D =250 mB1; h ₂₁ >80; 47 kOm/47 kOm	SOT23,SOD23	D.E.C





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
t08	PDTC144ET	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 mA; P _D =250 mBT; h ₂₁ >80; 47 кОм/47 кОм	SOT23,SOD23	B-E-C
t08	PDTC144EU	PHIL	Dnpn	V _{CRD} =50 B; I _C =100 mA; P _D =250 mBt; h ₂₁ >80; 47 kOm/47 kOm	SOT323,SC70	B·E·C
t09	PDTC114EU	PHIL	Dnpn	V _{CB0} =50 B; I _C =50 mA; P _D =250 mBT; h ₂₁ >30; 10 кОm/10 кОm	SOT323,SC70	B·E·C
TOKF	NDS0610	NS	pMOS	V _{DS} =60B; I _D =120 mA; P _D =360 mBT; R _{DS(on)} < 300 m	S0T23,S0D23	G•S•D
T1	BCX17	ALLEG	pnp	V _{CB0} =50B; I _{CB0} <100 HA; h ₂₁ =100600; V _{CE(sat)} <0.62B	SOT23,SOD23	B·E·C
T1	BCX17	CDIL	pnp	V_{CB0} =45 B; I_C =500 mA; P_D =250 mBT; h_{21} =100600; f_T >100 MF μ	SOT23,SOD23	B·E·C
T1	BCX17	ZETEX	pnp	V_{CB0} = 50 B; I_C = 500 mA; P_D = 330 mBT; h_{21} = 100600; f_T > 100 M Γ_{II}	SOT23,SOD23	B·E·C
T1	BSS63	MOT	pnp	V_{CB0} = 100 B; I_C =800 mA; P_D =330 mBT; h_{21} >30; f_T =150 MFu;	S0T23,S0D23	B·E·C
T1	HSMS2862	HP	shd×2	V _{BR} >5B;V _F (I _F =30 mA)<0.6B;C _T <0.30 mΦ; R _D =10 Om	SOT23,SOD23	A1 · K2 · K1,A2
T10	SSTPAD10	CALOG	dl	$V_R = 55B; I_R \le 10 \text{ MA}; V_R (I_R = 1 \text{ MA}) \le 1.5B; I_R \le 10 \text{ mA}; C_T \le 2 \text{ m}$	SOT23,SOD23	K·K·A
111	PDTA114TT	PHIL	Dpnp	V _{CB0} =50B; I _C =100 mA; P _D =200 mBT; h ₂₁ >200; R ₁ 10 kOm	SOT23,SOD23	B·E·C
T11	SSTPAD100	CALOG	dl	$V_B = 55B; I_E \le 10 \text{ mA}; V_E (I_E = 1 \text{ mA}) \le 1.5B; I_B \le 100 \text{ mA}; C_T \le 2 \text{ m}$	SOT23,SOD23	K·K·A
12	PDTC114TT	PHIL	Dnpn	V _{CBD} =50 B; I _C =100 mA; P _D =200 mBt; h ₂₁ >200; R ₁ 10 kOm	SOT23,SOD23	B·E·C
16	PDTC114ET	PHIL	Dnpn	V _{CBD} =50 B; I _C =50 mA; P _D =250 mBT; h ₂₁ >30; 10 кOm/10 кOm	S0T23,S0D23	B·E·C
17	PDTC124ET	PHIL	Dnpn	V _{CR0} =50B; I _C =100 mA; P _D =250 mBT; h ₂₁ >60; 22 kOm/22 kOm	SOT23,SOD23	B·E·C
18	PDTC143ZT	PHIL	Dnpn	V _{CRD} =50 B; I _C =100 mA; P _D =250 mBt; h ₂₁ >100; 4.7 кOm/47 кOm	SOT23,SOD23	
19	PDTA143ZT	PHIL	Dono	V _{GB0} =50 B; I _C =100 mA; P _D =250 mBr; h ₂₁ >100; 4.7 кOm/47 кOm	SOT23.SOD23	B·E·C
t1A	PMST3904	PHIL	non	V _{CR0} =60 B; I _C =200 mA; P _D =200 mBr; h ₂₁ =100300; f _T >300	S0T323.SC70	B·E·C
T1B	LM61BIM3	NS	ats	T _{AMR} =-2585 °C;V _{CC} =2.710 B;I _{CHT} <10 mA;ACC=±3°C	SOT23.SOD23	
t1B	PMBT2222	PHIL	non	V _{CBO} =60 B; I _C =600 мА; P _D =250 мВт; h ₂₁ =100300; f _T >250 МГц	S0T23,S0D23	
t1B	PMST2222	PHIL	non	V _{CBO} =60B; I _C =600 мА; Р _П =200 мВт; h ₂₁ =100300; f _T >250 МГц	S0T323.SC70	
TIC	LM61CIM3	NS	ats	T _{AMB} =-30100 °C;V _{CC} =2.710 B; I _{DUT} < 10 MA; ACC =± 4°C	SOT23.SOD23	
HD	PMBTA42	PHIL	non	V _{CBD} =300 B; I _G =500 мА; Р _D =250 мВт; h ₂₁ >40; f _T >50 МГц	SOT23,SOD23	
t1D	PMSTA42	PHIL	non	V _{CBO} =300 B; I _C =100 мА; P _D =200 мВт; h ₂₁ >40; f _T >50 МГц	S0T323,SC70	
1E	PMBTA43	MOT	non	V _{CR0} =200 B; I _C =500 мА; P _D =250 мВт; h ₂₁ >40; f _T >50 МГц	SOT23,SOD23	
t1E	PMSTA43	PHIL	non	V _{CR0} =200 B; I _C =300 MA; P _D =200 MBT; h ₂₁ >40; f _T >50 MFL	S0T323,SC70	
t1F	PMBT5550	PHIL	non	V _{CRD} =160 B; I _C =100 MA; P _D =250 MBT; h ₂₁ =60250; f _T =100300	SOT23,SOD23	(C)
t1F	PMST5550	PHIL	non	V _{CB0} =160 B; I _C =600 mA; P _D =200 mB; I _{R2} =60250; I _T =100300	SOT323,SC70	130-300 000
tir.	MMBTA05	PHIL	non	V _{CB0} =160 B; I _C =30 MA; P _D =350 MBT; h ₂₁ >50; f _T >100 MΓ _L	SOT23.SOD23	
HJ	PMBT2369	PHIL	non		SOT23,50D23	
t1K	PMBT6428	PHIL	non	V_{CB0} *40B; I_C *500 mA; P_D *250 mBT; h_{21} *40120 V_{CB0} *60B; I_C *200 mA; P_D *250 mBT; h_{21} *250650; f_T *100700 MF I_L	SOT23,SOD23	
t1L	PMBT6429	PHIL	-1		0.0000000000000000000000000000000000000	100000000000000000000000000000000000000
			npn	V _{CBO} =55B;I _C =200 мА;P _D =250 мВт;h ₂₁ =5001250;f _T =100700 МГц	S0T23,S0D23	1.0000000000
t1M	PMBTA13	PHIL	dnpn	V _{CB0} =30 B; I _C =300 mA; P _D =250 mBT; h ₂₁ >5000; f _T >125 MFu	S0T23,S0D23	70.71.71
t1N	PMBTA14	PHIL	dnpn	V_{CB0} =30 B; I_C =300 mA; P_D =250 mBT; h_{21} >10000; f_T >125 M Γ_{II}	S0T23,S0D23	
TIp	BCX17	PHIL	pnip	V _{CB0} =45B; I _C =500 мA; P _D =250 мBτ; h ₂₁ =100600; f ₁ >100 MΓ _{II}	S0T23,S0D23	
t1P	PMBT2222A	PHIL	npn	V _{CB0} =75B; I _C =600 мА; Р _D =250 мВт; h ₂₁ =100300; f _T >300 МГц	SOT23,SOD23	
-	PMST2222A	PHIL	non	V _{CB0} =75B; I _C =600 MA; P _D =200 MBT; h ₂₁ =100300; f _T >300 MFu	S0T323,SC70	DISTRICT.
1Q	PMBT5088	PHIL	npn	V _{CB0} =30 B; I _C =50 мA; P _D =250 мBт; h ₂₁ =3501400	S0T23,S0D23	100000000000000000000000000000000000000
1Q	PMST5088	PHIL	npn	V_{CB0} =35B; I_C =50 MA; P_D =200 MBT; h_{21} >300900	S0T323,SC70	2000
1R	PMST5089	PHIL	npn	V _{CB0} =30B; I _C =50 MA; P _D =200 MBT; h ₂₁ >4001200	S0T323,SC70	T. 100
T1t	BCX17	PHIL	pnjo	V _{CB0} =45B; I _C =500 мA; P _D =250 мВт; h ₂₁ =100600; f _T >100 МГц	S0T23,S0D23	
T2	BCX18	ALLEG	pnp	V _{CB0} =30B; I _{CB0} <100 нА;h ₂₁ =100600; V _{CE(sat)} <0.62B	S0T23,S0D23	
T2	BCX18	CDIL	pnp	$V_{CB0} = 25B; I_C = 500 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} = 100600; f_T > 100 \text{ MFu}$	S0T23,S0D23	
T2	BCX18	ZETEX	pnp	V_{CB0} = 30 B; I_C = 500 mA; P_D = 330 mBT; h_{21} = 100600; f_T > 100 MFU	S0T23,S0D23	
T2	HSMS286C	HP	shd×2	V _E (I _E =1 MA)<0.35B; C _T <0.30πΦ	S0T323,SC70	No. of the Part of
T2	TN2460T	SIL	nMOS	V _{DS} =240 B; I _D =51 mA; P _D =360 mBT; g _F =70 mCm; R _{DS(on)} =11 0m	SOT23,SOD23	
T20	SSTPAD20		dl	V _R =55 B; I _F <10 мA; V _F (I _F =1 мA)<1.5 B; I _R <20 πA; C _T <2 πΦ	SOT23,SOD23	V-100-000
T21	SSTPAD200	CALOG	dl	$V_R=55B$; $I_F < 10$ mA; $V_F(I_F=1$ mA) < 1.5 B; $I_R < 200$ nA; $C_T < 2$ n Φ	SOT23,SOD23	
23	PDTA114TU	PHIL	Dpnp	V _{CB0} =50B; I _C =100 мА; P _D =200 мВт; h ₂₁ >200; R ₁ 10 кОм	S0T323,SC70	
24	PDTC114TU	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBT; h ₂₁ >200; R ₁ 10 kOm	SOT323,SC70	
27	PDTC114YT	PHIL	Dnpn	V _{CB0} =50B; I _C =100 mA; P _D =200 mBT; h ₂₁ >100; 10 kOm/47 kOm	SOT23,SOD23	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
28	PDTA114WU	PHIL	Dpnp	V _{CR0} =50 B; I _C =100 mA; P _D =200 mBt; h ₂₁ >60; 47 кOm/22 кOm	S0T323,SC70	B-E-C
29	PDTA114YT	PHIL	Dono	V _{CR0} =50 B; I _C =100 mA; P _D =200 mBt; h ₂₁ >100; 10 kOm/47 kOm	SOT23,SOD23	
2A	PMBT3906	PHIL	pnp	V _{CBD} =40 B; I _C =200 мА; P _D =250 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	
2A	PMST3906	PHIL	pnp	V _{CP0} =40 B; I _C =200 MA; P _D =200 MBT; h ₂₁ =100300; f _T >250 MFu	SOT323.SC70	B-E-C
2B	PMBT2907	PHIL	pnp	V _{CB0} =60 B; I _C =600 мА; P _D =250 мВт; h ₂₁ >30; f _T >200 МГц	SOT23,SOD23	
t2D	PMBTA92	PHIL	ono	V _{CR0} =300 B; I _C =500 мА; P _D =250 мВт; h ₂₁ >40; f _T >50 МГц	SOT23.SOD23	100000000000000000000000000000000000000
t2D	PMSTA92	PHIL	onp	V _{сво} =300 B; I _c =100 мА; P _n =200 мВт; h ₂₁ >40; f _T >50 МГц	SOT323,SC70	B·E·C
t2E	PMBTA93	PHIL	ono	V _{CR0} =200 B; I _C =500 mA; P _D =250 mBr; h ₂₁ >40; f _T >50 MFu	SOT23,SOD23	
t2E	PMSTA93	PHIL	pnp	V _{CR0} =200 B, I _C =100 mA; P _D =200 mBr; h ₂₁ >40; f _T >50 MFu	S0T323.SC70	
t2F	PMBT2907A	PHIL	pnp	V _{CB0} =60 B; I _C =600 MA, P _D =250 MB; h ₂₁ >50; f _T >200 MFu	SOT23,SOD23	
t2G	PMBTA56	PHIL	onp	V _{CR0} =80 B; I _C =500 MA; P _D =250 MBT; h ₂₁ >50; f _T >50 MF _U	SOT23,SOD23	
t2G	PMSTA56	PHIL	ono	V _{CRN} =80 B; I _C =500 MA; P _D =200 MB; h ₂₁ >100; f _T >50 MF _{LL}	SOT323.SC70	175500000000
t2H	PMBTA55	PHIL	onp	V _{CB0} =60 B; I _C =500 мА; P _D =250 мВт; N ₂₁ >50; f _T >50 МГц	SOT23,SOD23	120,000,000
t2H	PMSTA55	PHIL	ono	V _{CBO} =60 B; I _C =500 мA; P _D =200 мB; I _{D2} >100; f _T >50 МГц	SOT323,30023	March 201
		PHIL	1 1			100000
t2L	PMBT5401		pnp	V _{GB0} =160 B; I _C =500 MA; P _D =250 MBT; h ₂₁ =60240; f _T =100300 MF _U	SOT23,SOD23	
t2L	PMST5401	PHIL	pnp	V _{GB0} =160 B; I _C =500 мA; P _D =200 мBт; h ₂₁ =60240; f _T =100300 МГц	SOT323,SC70	
T2p	BCX18	PHIL	pnp	V _{CB0} =25 B; I _C =500 мА; P _D =250 мВт; h ₂₁ =100600; f _T =100 МГц	SOT23,SOD23	
T2t	BCX18	PHIL	pnp	V _{CB0} =25 B; I _C = 500 мА, P _D =250 мВт; h ₂₁ = 100600; f _T = 100 МГц	SOT23,SOD23	70070070
t2T	PMBT4403	PHIL	pnp	V_{CB0} =40 B; I_C =600 mA; P_D =250 mBT; h_{21} =100300; f_T >200 M Γ_{IJ}	SOT23,SOD23	1150 115 130
t2T	PMST4403	PHIL	pnp	V_{CB0} =40 B; I_C =600 mA; P_D =200 mBT; h_{21} =100300; f_T >200 M Γ_{IJ}	S0T323,SC70	32232 22
t2U	PMBTA63	PHIL	dpnp	V_{CB0} =30 B; I_C =500 mA; P_D =250 mBT; h_{21} >5000; f_T >125 M Γ μ	SOT23,SOD23	
t2V	PMBTA64	PHIL	dpnp	V_{CB0} =30 B; I_C =500 mA; P_D =250 mBT; h_{21} >10000; f_T >125 M Γ_{II}	SOT23,SOD23	
t2X	PMBT4401	PHIL	npn	V _{GB0} =40 B; I _C =600 мA; P _D =250 мВт; h ₂₁ =100300; f _T > 250 МГц	SOT23,SOD23	B·E·C
t2X	PMST4401	PHIL	npn	V_{CB0} =60 B; I_C =600 mA; P_D =200 mBT; h_{21} =100300; f_T >250 MFu	SOT323,SC70	B·E·C
T3	BSS63	PHIL	pnp	V_{CB0} =100 B; I_C =800 mA; P_0 =330 mBr; h_{21} >30; f_7 =150 M Γ_{II}	SOT23,SOD23	B-E-C
T3	HSMS 2863	HP	shd×2	V _{BR} >5 B; V _F (I _F =30 мА) < 0.6 B; C _T < 0.30 пФ; R _D = 10 Ом	SOT23,SOD23	K1·K2·A1,A2
T3	HSMS286E	HP	shd×2	V _E (I _E =1 MA) < 0.35 B; C _T < 0.30 nΦ	SOT323,SC70	K1 · K2 · A1, A2
t30	PDTC114YU	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 мА; P _D =200 мВт; h ₂₁ >100; 10 кОм/47 кОм	SOT323,SC70	B·E·C
t31	PDTA143XT	PHIL	Dpnp	V _{GB0} =50 B; I _G =100 мА; P _D =250 мВт; h ₂₁ >50; 4.7 кОм/10 кОм	SOT23,SOD23	B·E·C
T32	2SC4182	NEC	npn	V _{CB0} =30 B; I _C =50 mA; P _D =160 mBt; h ₂₁ =60105; f _T =1.1 FTu	SOT323,SC70	B-E-C
t32	PDTC143XT	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 мА; P _D =250 мВт; h ₂₁ >50; 4.7 кОм/10 кОм	SOT23,SOD23	B·E·C
T33	2SC4182	NEC	non	V _{сво} =30 B; I _C =50 мА; Р _О =160 мВт; h ₂₁ =85150; f _T =1.1 ГГц	SOT323,SC70	B·E·C
T34	2SC4182	NEC	npn	V _{сво} =30 B; I _c =50 мA; P _n =160 мВт; h ₂₁ =120220; Г _т =1.1 ГГц	SOT323,SC70	
T35	BSR20	CDIL	ono	V _{GB0} =130 B; I _G =600 mA; P _D =250 mBr; h ₂₁ >40; f _T =400 MFu	SOT23,SOD23	
T35	BSR20	PHIL	pnp	V _{CR0} =130 B; I _C =600 mA; P _D =250 mBr; h ₂₁ >40; f _T =100400 MFu	SOT23,SOD23	
T36	BSR20A	CDIL	ono	V _{GB0} =160 B; I _C =600 мА; P ₀ =250 мВт; h ₂₁ >60; f ₁ =300 МГц	SOT23,SOD23	
T36	BSR20A	PHIL	ono	V _{CR0} =160 B; I _C =600 MA; P _D =250 MB; I _{P2} >60; f _T =100300 MFu	SOT23,SOD23	SA RESCUE
T4	BCX17R	ZETEX	onp	V_{CB0} =50 B; I_C =500 mA; P_0 =330 mB τ ; h_{21} =100600; f_T >100 MF ϕ	SOT23,SOD23	100,000,000
T4	BCX17R	PHIL	ono	V_{CB0} =45 B; I_C =500 mA; P_D =250 mBt; h_{21} =100600; f_T >100 MFц	SOT23,SOD23	
T4	HSMS2864	HP	shd×2	V _{BR} > 5 B; V _E (I _E =30 mA) < 0.6B; C _T < 0.30 πΦ; R _D =10 0 m	SOT23,SOD23	
T4	HSMS286F	HP	shd×2	V _E (I _E =1 mA) < 0.35 B; C _T < 0.30 nΦ	SOT323,SC70	
T42	2SC4184	NEC			SOT323,SC70	-
T43			npn	V _{CBB} =30 B; I _C =50 мA; Р _B =160 мВт; h ₂₁ =4080; f _T >1.2 ГГц		
	2SC4184	NEC	npn	V _{CB0} =30 B; I _C =50 MA; P _D =160 MBT; h ₂₁ =60120; f _T >1.2 [T _U	SOT323,SC70	
T44	2SC4184	NEC	npn	V _{GB0} =30 B; I _G =50 MA; P ₀ =160 MBr; h ₂₁ =100200; f _T >1.2 ITu	SOT323,SC70	1,000-000-000
t46	PDTA143XU	PHIL	Dpnp	V _{GB0} =50 B; I _G =100 mA; P _D =250 mBT; h ₂₁ >50; 4.7 κOm/10 κOm	S0T323,SC70	750.077 03
t47	PDTA143ZU	PHIL	Dpnp	V _{CB0} =50 B; I _C =100 мА; P _D =250 мВт; h ₂₁ >100; 4.7 кОм/47 кОм	S0T323,SC70	155.55
T4B	LM45BIM3	NS	ats	T _{AMB} =-20100°C;V _{CC} =410 B;I _{OUT} <10 mA	SOT23,SOD23	
T4C	LM45CIM3	NS	ats	T _{AMB} =-20100°C;V _{CC} =410 B;I _{OUT} <10 mA	SOT23,SOD23	
T5	BCX18R	ZETEX	pnp	V_{CB0} =30 B; I_C =500 mA; P_D =330 mBT; h_{21} =100600; f_T >100 MF $_{II}$	SOT23,SOD23	
T5	BCX18R	PHIL	pnp	V_{CB0} =30 B; I_C =500 mA; P_D =330 mBT; h_{21} =100600; f_T >100 M Γ_{II}	SOT23,SOD23	100000000000000000000000000000000000000
T50	SSTPAD50	CALOG	dl	$V_R = 55 B; I_F \le 10 \text{ mA}; V_R (I_F = 1 \text{ mA}) \le 1.5 B; I_R \le 50 \text{ nA}; C_T \le 2 \text{ n} \Phi$	SOT23,SOD23	K•K•A
53	PDTC143XU	PHIL	Dnpn	V _{CB0} =50 B; I _C =100 мA; P _D =250 мВт; h ₂₁ >50; 4.7 кОм/10 кОм	SOT323,SC70	B-E-C





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
154	PDTC143ZU	PHIL	Dnpn	V _{CRD} =50 B; I _C =100 mA; P _D =250 mBt; h ₂₁ >100; 4.7 kOm/47 kOm	SOT323,SC70	B·E·C
55	PDTA114YU	PHIL	Donio	V _{CR0} =50B; I _C =100 mA; P _D =200 mBt; h ₂₁ >100; 10 kOm/47 kOm	SOT323,SC70	B·E·C
T5B	LM50BIM3	NS	ats	T _{AMB} =-40125 °C; V _{CC} =4.510 B; I _{OUT} < 10 mA ; ACC =± 2°C	SOT23,SOD23	
T5C	LM50CIM3	NS	ats	T _{AMB} =-40125°C;V _{CC} =4.510 B; I _{OUT} < 10 mA; ACC =± 3°C	SOT23.SOD23	+Vs •Vo•GND
T6	BSS63R	PHIL	pnp	V _{CRO} =100 B; I _C =800 мА; P _D =330 мВт; h ₂₁ >30; f _T =150 МГц	SOT23,SOD23	E-B-C
T61	ZUMT617	ZETEX	non	V _{CBD} = 15B; l _C = 1.5 A; P _D =385 мВт; h ₂₁ > 30; f _T = 180 МГц	SOT323,SC70	120000000000000000000000000000000000000
T62	2SC3841P	NEC	non	V _{CB0} = 25 B; I _C = 30 мА; P _D = 200 мВт; h ₂₁ = 4080; f _T > 2.5 ГГц	SOT23,SOD23	B·E·C
T62	2SC4186	NEC	non	V _{CR0} =25B; I _C =30 MA; P _D =160 MBT; h ₂₁ =4080; f _T >2.5 ΓΓ _U	SOT323,SC70	B-E-C
T62	ZUMT618	ZETEX	non	V _{GBO} = 20B; I _C = 1.25 A; P _D =385 мВт; h ₂₁ > 20; f _T = 210 МГц	SOT323,SC70	
T63	2SC3841Q	NEC	non	V _{GB0} =25B; I _C =30 мA; P _D =200 мВт; h ₂₁ =60120; f ₁ >2.5 ГГц	SOT23.SOD23	
T63	2SC4186	NEC	non	V _{CBD} = 25 B; I _C = 30 мА; P _D = 160 мВт; h _{P1} =60120; f _T > 2.5 ГГц	SOT323,SC70	
T63	ZUMT619	ZETEX	non	V _{CB0} =50 B; I _C =1 A; P _D =385 мВт; h ₂₁ >20; f _T =215 МГц	SOT323.SC70	1000127551191
T64	2SC3841R	NEC	non	V _{CBO} =25B; I _C =30 мA; P _D =200 мВт; h ₂₁ =100200; f _T >2.5ГГц	SOT23,SOD23	0.0000000000000000000000000000000000000
T64	2SC4186	NEC	non	V _{CBD} =25B; I _C =30 MA; P _D =160 MBT; h ₂₁ =100200; f _T >2.5FFu	SOT323.SC70	100000000000000000000000000000000000000
T6B	LM60BIM3	NS	ats	T _{AMB} =-25125 'C; V _{CC} =4.510 B; I _{DUT} < 10 MA; ACC =± 3'C	SOT23.SOD23	CC - CC - CC
T6C	LM60CIM3	NS	ats	T _{AMB} =-40125 °C;V _{CC} =4.510 B;I _{DUT} < 10 MA; ACC=2 5 C	SOT23,SOD23	
17	BSR15	CDIL	onp	V _{CBD} =60B; I _C =600 мА; P _D =250 мВт; h ₂₁ >30; f _T >200МГц	SOT23,SOD23	
17	BSR15	SGS	prip	V _{CB0} =60 B; I _C =600 MA; P _D =250 MB; h ₂₁ >30; f _T >200 MFц	SOT23,SOD23	
17	SST4117	SIL	nFET	V _{DS} =40 B; P _D =350 MB; I _{DSS} =0.030.09 MA; g _F =70 MCM	SOT23,SOD23	
171	BSR15R	SGS	pnp	V _{CRO} =60 B; I _C =600 мА; P _D =250 мВт; h _{P1} >30; f _T >200 МГц	SOT23,SOD23	TAUX TO
171	ZUMT717	ZETEX		000		1,000,000
T72			pnp	V _{CBO} =12B;I _C =1.25A;P _O =385mBt;h ₂₁ >30;f ₁ =220Mfu	SOT323,SC70	
	2SC4568	NEC	npn	V _{CB0} =20B;I _C =30 MA;P _D =150 MBT;h ₂₁ =4080;f _T =5.5 FT _U	SOT23,SOD23	
172	2SC4570	NEC	npn	V _{C80} =20B; I _C =30 mA; P _D =120 mBT; h ₂₁ =4080; f _T =5.5 TTu	SOT323,SC70	
72	ZUMT718	ZETEX	pnp	V _{CB0} =20B; I _C =1A; P _D =385 MBT; h ₂₁ >20; f _T =210 MFц	SOT323,SC70	
73	2SC4568	NEC	npn	V _{CB0} =20B; I _C =30 мА; P _D =150 мВт; h ₂₁ =60120; f _T =5.5 ГГц	SOT23,SOD23	
173	2SC4570	NEC	npn	V _{CBO} =20B; I _C =30 мА; P _D =120 мВт; h ₂₁ =60120; f _T =5.5 ГГц	S0T323,SC70	T0171171
T73	ZUMT719	ZETEX	pnp	V _{C80} =40B; I _C =1A	SOT323,SC70	
174	2SC4568	NEC	npn	V _{CB0} =20B; I _C =30 мА; P _D =150 мВт; h ₂₁ =100200; f _T =5.5 ГГц	SOT23,SOD23	
T74	2SC4570	NEC	npn	V _{СВ0} =20B; I _C =30 мА; Р ₀ =120 мВт; h ₂₁ =100200; f _T =5.5 ГГц	SOT323,SC70	
175	2SC4569	NEC	npn	V _{C80} =20B; I _C =60 мA; P _D =150 мВт; h ₂₁ =4080; f _T =5 ГГц	SOT23,SOD23	
T75	2SC4571	NEC	npn	V_{C80} =20B; I_C =60 MA; P_D =120 MBT; h_{21} =4080; f_T =5 ГГц	SOT323,SC70	1000000000000
175	NE58230	NEC	npn	V_{CB0} = 20 B; I_C = 60 MA; P_D = 120 MBT; h_{21} =4080; f_T =5 ГГц	SOT323,SC70	
T76	2SC4569	NEC	npn	V _{CB0} =20 B; I _C =60 мA; P _D =150 мВт; h ₂₁ =60120; f _T =5 ГГц	SOT23,SOD23	B·E·C
T76	2SC4571	NEC	npn	V _{CB0} =20 B; I _C =60 MA; P _D =120 MBT; h ₂₁ =60120; f _T =5 ГГц	SOT323,SC70	B·E·C
T76	NE58230	NEC	npn	V _{CB0} =20B; I _C =60 мA; P _D =120 мВт; h ₂₁ =60120; f _T =5ГГц	SOT323,SC70	B·E·C
177	2SC4569	NEC	npn	V_{C80} =20B; I_C =60 MA; P_D =150 MBT; h_{21} =100200; f_T =5 FF $_{II}$	SOT23,SOD23	B·E·C
177	2SC4571	NEC	npn	V _{CB0} =20B; I _C =60 MA; P _D =120 MBT; h ₂₁ =100200; f _T =5 ГГц	SOT323,SC70	B·E·C
177	NE58230	NEC	npn	V _{C80} =20B; I _C =60 мA; P _D =120 мВт; h ₂₁ =100200; f _T =5ГГц	SOT323,SC70	B·E·C
T7B	LM62BIM3	NS	ats	T _{AMB} =090°C;V _{CC} =2.710B;I _{DUT} <10 MA;ACC=±2°C	SOT23,SOD23	+Vs •Vo•GND
T7C	LM62CIM3	NS	ats	T _{AMB} =090°C; V _{CC} =2.710B; I _{OUT} < 10 MA; ACC=±3°C	SOT23,SOD23	+Vs •Vo•GND
T7p	BSR15	PHIL	pnip	V _{CR0} =60B; I _C =600 mA; P _D =250 mBT; h ₂₁ >30; f _T >200 MFц	SOT23,SOD23	B·E·C
17t	BSR15	PHIL	pnp	V _{CRD} =60 B; I _C =600 мА; P _D =250 мВт; h ₂₁ >30; f _T >200 МГц	SOT23,SOD23	B·E·C
7Y	PDTB123YT	PHIL	Dpnp	V _{CBD} =50 B; I _C =500 mA; P _D =250 mBt; h ₂₁ >70; 2.2 kOm/10 kOm	SOT23,SOD23	B-E-C
T8	BSR16	CDIL	onp	V _{CB0} =60B; I _C =600 мА; P _D =250 мВт; h ₂₁ >50; f _T > 200 МГц	SOT23,SOD23	B·E·C
18	BSR16	SGS	pnp	V _{CB0} =60 B; I _C =600 мА; P _D =250 мВт; h ₂₁ >50; f _T >200 МГц	SOT23,SOD23	1000010101
T8	SST4118	SIL	nFET	V _{DS} =40 B;P _D =350 mB _T ;I _{DSS} =0.080.24 mA;g _F =80 mCm	SOT23,SOD23	
T81	BSR16R	SGS	onp	V _{CB0} =60B; I _C =600 мА; Р _П =250 мВт; h ₂₁ >50; f _T >200 МГц	SOT23.SOD23	02 - 52 - 52
182	2SC4954	NEC	non	V _{CBO} =9B; I _C =10мA; P _D =60мBт; I _{D21} =75150; f _T =12ГГц	SOT23,SOD23	
182	2SC4958	NEC	non	V _{CBO} =9B; I _C =10мA; P _П =60мВт; h ₂₁ =75150; f ₁ =12ГГц	SOT323,SC70	
183	2SC4955	NEC	non	V _{CB0} =9B; I _C =30мA; P _D =180мBт; h ₂₁ =75150; f _T =12ГГц	SOT23,SOD23	
T83	2SC4959	NEC	non	V _{CBO} =9B;I _C =30mA;P _D =150mB;t ₁ t ₂ =75100;f ₇ =12ΓΓц	S0T323,SC70	100000000000000000000000000000000000000
T84	2SC5177	NEC	non	V _{CR0} =5 B; I _C =10 MA; P _D =30 MBT; h ₂₁ =70140; f _T >10 ΓΓ I _I	SOT23,SOD23	1.0153.03.02

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
T84	2SC5179	NEC	npn	V _{CB0} =5 B; I _C =10 мA; P _D =30 мВт; h ₂₁ =70140; f _T >10 ГГц	SOT323,SC70	B-E-C
T86	2SC5182	NEC	npn	V _{CB0} =5 B; I _C =30 мA; P _D =90 мВт; h ₂₁ =70140; f _T >9 ГГц	SOT23,SOD23	B-E-C
T86	2SC5184	NEC	npn	V _{CB0} =5 B; I _C =30 мА; Р _D =90 мВт; h ₂₁ =70140; f _T >9 ГГц	S0T323,SC70	B-E-C
T88	2SC5191	NEC	npn	V _{CB0} =9 B; I _C = 100 мА; P _D = 200 мВт; h ₂₁ =80160; f _T >4 ГГц	SOT23,SOD23	B-E-C
T88	2SC5193	NEC	npn	V _{CB0} =9 B; I _C = 100 мА; Р ₀ = 150 мВт; h ₂₁ =80160; f _T >4 ГГц	SOT323,SC70	B-E-C
Т8р	BSR16	PHIL	pnp	V_{CB0} =60 B; I_C =600 mA; P_D =250 mBT; h_{21} >50; f_T >200 M Γ_{IL}	SOT23,SOD23	B-E-C
T8t	BSR16	PHIL	pnp	V_{CB0} =60 B; I_C =600 mA; P_D =250 mBT; h_{21} >50; f_T >200 MFu	SOT23,SOD23	B-E-C
Т9	1SS396	TOSH	shd×2	V _B >40 B; V _E (I _F = 100 mA) < 0.6 B; I _E (V _B =40 B) < 5 mkA; C _T < 25 nΦ	SOT346,SC59	A1-K2-K1,A2
T9	SST4119	SIL	nFET	V _{DS} =40 B; P _D =350 мВт; I _{DSS} =0.20.6 мА; g _F =100 мСм	SOT23,SOD23	D·S·G
T92	2SA1977	NEC	onp	V _{CB0} =20 B; I _C =50 мА; P _D =200 мВт; h ₂₁ =20100; f _T >6ГГц	SOT23,SOD23	B-E-C
T92	BSR18A	CDIL	pnp	V_{CB0} =40 B; I_C =200 mA; P_D =250 mBT; h_{21} =100300; f_T >250 MFu	SOT23,SOD23	B-E-C
T92	BSR18A	FAIR	pnp	V_{CB0} =40 B; I_C =200 mA; P_D =250 mBT; h_{21} =100300; f_T >250 MFu	SOT23,SOD23	B-E-C
T92	NE97733	NEC	pnp	V _{CB0} =20 B; I _C =50 мА; P _D =200 мВт; h ₂₁ =20100; f ₁ =8.5 ГГц	SOT23,SOD23	B-E-C
Т92р	BSR18A	PHIL	pnp	V_{CB0} =40 B; I_C =200 mA; P_D =250 mBT; h_{21} =100300; f_T >250 MF $_{LL}$	SOT23,SOD23	B-E-C
T93	2SA1978	NEC	pnp	V _{CB0} =20 B; I _C =50 мА; P _D =200 мВт; h ₂₁ =20100; f _T >4 ГГц	SOT23,SOD23	B-E-C
T93	NE97833	NEC	pnp	V _{CB0} =20 B; I _C =50 mA; P _D =200 mBt; h ₂₁ =20100; f _T =5.5 FFu	SOT23,SOD23	B-E-C
19A	PLVA650A	PHIL	dz	$V_2(I_{ZT}=250 \text{ m/sA})=4.85.2 \text{ B}, I_L(V_B=0.8^{\circ}V_Z)<20 \text{ m/sA}, Z_{ZT}(I_{ZT}=250 \text{ m/sA})<700 \text{ Om}, I_{ZM}=250 \text{ m/s}$	SOT23,SOD23	A·n.c.·K
19 B	PLVA653A	PHIL	dz	$V_Z(I_{ZT}=250 \text{ m/A})=5.15.5 \text{ B}, I_{1}(V_{B}=0.8^{\circ}V_{Z})<5 \text{ m/A}; $ $Z_{ZT}(I_{ZT}=250 \text{ m/A})<250 \text{ Om}, I_{ZM}=250 \text{ MA}$	SOT23,SOD23	A•n.c.•K
19C	PLVA656A	PHIL	dz	$V_Z(I_{ZT}=250 \text{ m/A})=5.45.8 \text{ B}, I_L(V_0=0.8^{\circ}V_Z) \le 1 \text{ m/A};$ $Z_{ZT}(I_{ZT}=250 \text{ m/A}) \le 100 \text{ Om}; I_{ZM}=250 \text{ m/A}$	SOT23,SOD23	A·n.c.·K
19 D	PLVA659A	PHIL	dz	$V_Z(I_{ZT}=250 \text{ mKA})=5.76.1 \text{ B}(I_L(V_B=0.8^{\circ}V_Z)<500 \text{ HA}; \\ Z_{ZT}(I_{ZT}=250 \text{ mKA})<100 0 \text{ m}; I_{ZM}=250 \text{ mA}$	SOT23,SOD23	A·n.c.·K
9 E	PLVA662A	PHIL	dz	V _Z (I _{ZT} =250 mKA)=6.06.4B;I _L (V _R =0.8°V _Z)<100 HA; Z _{ZT} (I _{ZT} =250 mKA)<100 Om;I _{ZM} =250 mA	SOT23,SOD23	A·n.c.·K
9F	PLVA665A	PHIL	dz	V _Z (I _{ZT} =250 mKA)=6.36.7 B;I _L (V _R =0.8°V _Z)<50 HA; Z _{ZT} (I _{ZT} =250 mKA)<100 Om;I _{ZM} =250 mA	SOT23,SOD23	A·n.c.·K
19 G	PLVA668A	PHIL	dz	V _Z (I _{ZT} =250 mKA)=6.67.0 B;I _L (V _R =0.8°V _Z)<10 HA; Z _{ZT} (I _{ZT} =250 mKA)<100 Om;I _{ZM} =250 mA	SOT23,SOD23	A·n.c.·K
19J	PLVA2650A	PHIL	dz×2	$V_2(I_{ZT}=250 \text{ mKA})=4.85.2 \text{ B}; I_1(V_p=0.8^*V_Z)<20 \text{ mKA}; Z_{ZT}(I_{ZT}=250 \text{ mKA})<700 \text{ OM}; I_{ZM}=250 \text{ mA}$	SOT23,SOD23	K1 · K2 · A1, A2
9K	PLVA2653A	PHIL	dz×2	V _Z (I _{ZT} =250 mKA)=5.15.5 B;I _L (V _R =0.8°V _Z)<5 mKA; Z _{ZT} (I _{ZT} =250 mKA)<250 OM;I _{ZM} =250 mA	SOT23,SOD23	K1-K2-A1,A2
19 L	PLVA2656A	PHIL	dz×2	$V_Z(I_{ZT}=250 \text{ mKA})=5.45.8 \text{ B}; I_L(V_R=0.8^{\circ}V_Z)<1 \text{ mKA}; \\ Z_{ZT}(I_{ZT}=250 \text{ mKA})<100 0 \text{ m}; I_{ZM}=250 \text{ mA}$	SOT23,SOD23	K1-K2-A1,A2
9M	PLVA2659A	PHIL	dz×2	$V_2(I_{ZT}=250 \text{ mKA})=5.76.1 \text{ B}, I_1(V_R=0.8^*V_Z)<500 \text{ HA}; Z_{ZT}(I_{ZT}=250 \text{ mKA})<100 \text{ OM}; I_{ZM}=250 \text{ mA}$	SOT23,SOD23	K1-K2-A1,A2
9N	PLVA2662A	PHIL	dz×2	$V_Z(I_{ZT}=250 \text{ m/s})=6.06.4 \text{B}, I_L(V_R=0.8^{\circ}V_Z) \le 100 \text{ hA};$ $Z_{ZT}(I_{ZT}=250 \text{ m/s}) \le 100 \text{ Om}; I_{ZM}=250 \text{ mA}$	SOT23,SOD23	K1 · K2 · A1, A2
90	PLVA2665A	PHIL	dz×2	$V_Z(I_{ZT} = 250 \text{ m/s}) = 6.36.7 \text{ B}_1I_4(V_B = 0.8^4V_Z) \le 50 \text{ m/s};$ $Z_{ZT}(I_{ZT} = 250 \text{ m/s}) \le 100 \text{ 0 m}; I_{ZM} = 250 \text{ m/s}$	SOT23,SOD23	K1 · K2 · A1, A2
19 P	PLVA2668A	PHIL	dz×2	$V_Z(I_{ZT} = 250 \text{ m/s}) = 6.67.0 \text{ B}_1I_4(V_B = 0.8^4V_Z) \le 10 \text{ HA};$ $Z_{ZT}(I_{ZT} = 250 \text{ m/s}) \le 100 \text{ Om}; I_{ZM} = 250 \text{ m/s}$	SOT23,SOD23	K1-K2-A1,A2
TA	2SC5431EB	NEC	npn	V _{CB0} =20 B; I _C =60 mA; P ₀ =100 mBr; h ₂₁ =6090; f _T >3 TFu,	SC81,MFPAK	B·E·C
TA	KTC3295A	KEC	npn	V _{CB0} =60 B; I _C = 150 мА; P _D =150 мВт; h ₂₁ =6001800; f _T >250 МГц	SOT23,SOD23	B·E·C
TA	NE582M03	NEC	npn	V _{CB0} =20 B; I _C =60 мA; P ₀ =100 мВт; h ₂₁ =6090; f _T =4.3 ГГц	SC81,MFPAK	B·E·C
TA5	MMBZ15VDA	VISH	dz×2	V ₂ (I _{ZT} =1 mA)=14.715.3B; V _F (I _F =200 mA)<0.9B	SOT23,SOD23	K1·K2·A1,A2
TA7	MMBZ27VDA	VISH	dz×2	V ₂ (I _{ZT} =1 mA)=26.4627.54 B; V _E (I _E =200 mA) < 1.1 B	SOT23,SOD23	K1·K2·A1,A2
TAA	BC856AF	AUK	pnp	V _{CB0} =80 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =110220; f _T =150 МГц	SOT490,SC89	B·E·C
TAB	BC856BF	AUK	pnp	V _{GB0} =80 B; I _G =100 мА; P _D =200 мВт; h ₂₁ =200450; f _T =150 МГц	SOT490,SC89	B·E·C
TAC	BC856CF	AUK	onp	V _{GB0} =80 B; I _G =100 мА, P _D =200 мВт; h ₂₁ =420800; f _T =150 МГц	SOT490,SC89	B·E·C
ТВ	2SC5431FB	NEC	npn	V _{CR0} =20 B; I _C =60 mA; P _D =100 mBr; h ₂₁ =80120; f _T >3 FF _U		B·E·C
ГВ	KTC3295B	KEC	nan	V _{CR0} =60 B; I _C =150 мA; P _D =150 мBт; h ₂₁ =12003600; f _T >250 МГц	SOT23,SOD23	7 7 3
TBD	BAT46CW	STM	shd×2	V _R <100 B; I _E <150 MA; V _E (I _E =10 MA)<0.45 MB; C _D =10 nΦ	S0T323.SC70	





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
TBD	BAT46SW	STM	shd-2	V _R <100 B;I _F <150 mA; V _F (I _F =10 mA)<0.45 mB; C _D =10 πΦ	SOT323,SC70	A2-K1-A1,K2
TC	2SC2736	REN	non	V _{CRD} =30B; I _C =50 мА; P _D =150 мВт; h ₂₁ =30200; f ₁ >1.4ГГц	SOT346,SC59	B·E·C
TC	2SC5432EB	NEC	non	V _{CP0} =20B; I _C =100 mA; P _D =125 mBr; h ₂₄ =80110; f _T >3 ГГц	SC81,MFPAK	B·E·C
TC5	MMBZ15VDC	VISH	dz×2	V _z (I _{zz} =1 mA)=14.315.8B;V _E (I _E =200 mA)<0.9B	SOT23.SOD23	A1 • A2 • K1, K2
TC7	MMBZ27VDC	VISH	dz×2	V _z (I _{zz} =1 mA)=26.6528.35B; V _e (I _E =200 mA) < 1.1B	SOT23,SOD23	A1-A2-K1,K2
TD	2SC5432FB	NEC	non	$V_{CB0} = 20B_1I_C = 100 \text{ mA}, P_0 = 125 \text{ mBT}, h_{21} = 100145; f_1 > 3 \Gamma \Gamma L$	SC81.MFPAK	B-E-C
TE	2SC3906KE	ROHM	non	V _{CRO} = 120 B; I _C =50 мА; P _D =200 мВт; h ₂₁ =390820; f ₇ > 140 МГц	SOT346,SC59	B·E·C
TE	2SC4102E	ROHM	non	V _{CR0} = 120 B; I _C =50 mA; P _D =200 mBτ; h ₂₁ =390820; f ₇ > 140 MΓц	SOT323,SC70	10 10 10
TE	2SC5433EB	NEC	non	V _{CB0} =20B; I _C =65 мA; P _D =125 мВт; h ₂₁ =80110; f ₁ >4.5 ГГц		B·E·C
TF	2SC5433FB	NEC	npn	V _{CB0} =20B; I _C =65 MA; P _D =125 MBT; h ₂₁ =100145; f _T >4.5 ГГц		B-E-C
G1	PMBT5551	PHIL	non	V _{CB0} =180 B; I _G =600 mA; P _D =250 mBT; h ₂₁ =80250; f _T =100300	SOT23,SOD23	
tG3	PMST5551	PHIL	non	V _{CB0} =180 B; I _C =600 мА; P _D =200 мВт; h ₂₁ =80250; f _T =100300 МГц	SOT323,SC70	
TH	2SC5434EB	NEC	non	V _{сеп} =20В; I _с =35мA; Р _п =125 мВт; h ₂₁ =80110; f ₇ >5.5ГГц	-	B·E·C
TI	2SC4197	REN	non	V _{CBD} =250; I _C =50 MA; P _D =150 MBT; I _{D2} =50180; I _T >3 ITI _L	SOT346,SC59	122000000000000000000000000000000000000
TI TI	2SC4260	REN	non	V _{CR0} -25B, I _C -50 MA; P _D -130 MB; I _D -150180; I _T >3 ITu	SOT323.SC70	
TJ	2SC5434FB	NEC	non		-	B·E·C
			- de co	V _{CBO} =20B; I _C =35 MA; P _D =125 MBT; h ₂₁ =100145; f _T >5.5 FT _U		
TK	2SC5435EB	NEC	npn	V _{CBO} =9B; I _C =30mA, P _D =125mBT; h ₂₁ =75110; f _T =12ΓΓц	and a property of	B·E·C
TL	2SC5435FB	NEC	npn	V _{CB0} =9B;I _C =30mA;P _D =125mBT;h ₂₁ =95140;f _T =12ΓΓц	E-E-A-Maria	B-E-C
TN	2SC5436EB	NEC	npn	V _{CB0} =5B; I _C =30мA; P _D =90мBт; h ₂₁ =75100; f _T >9 ГГц		B·E·C
TO	TP0610T	TEMIC	pMOS	V _{DS} =60 B;I _D =120 мA; P _D =360 мВт; g _E =60 мСм; R _{DS(on)} =10 0м	SOT23,SOD23	100,000 000
TO	TP0610T	SIL	pMOS	V _{DS} =60 B;I _D =120 мA;P _D =360 мВт;g _F =60 мСм;R _{DS(o1)} =10 Ом	SOT23,SOD23	
t04	PMBS3904	PHIL	npn	V_{CB0} =60B; I_C =100 mA; P_0 =250 mBT; h_{21} =100300; f_T >180 MF $_{II}$	SOT23,SOD23	
t06	PMBS3906	PHIL	pnp	V_{CB0} =40B; I_C =100 mA; P_D =250 mBT; h_{21} =100300; f_T >150 MF μ	SOT23,SOD23	100000000000000000000000000000000000000
TP	2SC5436FB	NEC	non	V_{CB0} =5B; I_C =30mA; P_D =90mBT; h_{21} =90130; f_T >9 $\Gamma\Gamma I_L$		B·E·C
TR	2SC3906KR	ROHM	non	V_{CB0} = 120 B; I_C = 50 mA; P_D = 200 mBT; h_{21} = 180390; f_T > 140 MFu	SOT346,SC59	B·E·C
TR	2SC3929AR	PAN	non	V _{CB0} =55 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =180360; f _T =100 МГц	SOT323,SC70	B.E.C
TR	2SC4102R	ROHM	npn	V_{CB0} = 120 B; I_C = 50 mA; P_D = 200 mBT; h_{21} = 180390; f_T > 140 MFu,	SOT323,SC70	B-E-C
TS	2SC3906KS	ROHM	npn	V_{CB0} * 120 B; I_C * 50 mA; P_0 * 200 mBT; h_{21} * 270560; f_1 > 140 MFu	SOT346,SC59	B·E·C
TS	2SC3929AS	PAN	npn	V _{CB0} =55 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =260520; f _T =100 МГц	SOT323,SC70	B·E·C
TS	2SC4102S	ROHM	npn	V_{CB0} = 120 B; I_C =50 mA; P_D =200 mBT; h_{21} =270560; f_T >140 M Γ_{II}	SOT323,SC70	B.E.C
TS	2SC5437EB	NEC	npn	V _{CB0} =9B;I _C =100 мA;P _D =125 мВт;h ₂₁ =80110; f ₁ >4 ГГц	SC81 MFPAK	B-E-C
П	2SC3929AT	PAN	npn	V _{CBD} =55 B; I _C =50 мA; P _D =150 мВт; h ₂₁ =360700; f _T =100 МГц	SOT323,SC70	B·E·C
П	2SC5437FB	NEC	non	$V_{CB0}=9B;I_{C}=100 \text{ mA};P_{D}=125 \text{ mBT};h_{21}=100145;f_{T}>4 \Gamma\Gamma_{U}$	SC81,MFPAK	B·E·C
TV	2SC5599	NEC	npn	V _{CRD} =9B; I _C =100 mA; P _D =200 mBT; h ₂₁ =80160; f _T >3.5 ГГц	SOT416,SC75A	B·E·C
TV	2SC5600	NEC	non	V _{CBB} *5.5 B; I _C *15 mA; f _T *5.5 ГГц	SOT346,SC59	B·E·C
tV3	BAT54A	PHIL	shd×2	V _B <30 B; I _E <200 mA; V _E (I _E =30 mA)<500 mB; C _D <10 nΦ; t _{BB} <5 hc	SOT23.SOD23	K1-K2-A1.A2
V4	BAT54S	PHIL	shd×2	$V_B < 30 B; I_E < 200 \text{ mA}; V_B (I_E = 30 \text{ mA}) < 500 \text{ mB}; C_D < 10 \text{ n}\Phi; t_{BB} < 5 \text{ hc}$	SOT23,SOD23	A1-K2-K1.A2
TW	2SC5602	NEC	non	V _{GB0} =15B; I _C =35мA; P _D =200 мВт; h ₂₁ =60120; f ₁ >12 ГГц	SOT416.SC75A	No. of the Control of
TW	2SC5603	NEC	non	V _{CB0} =6B; I _C =15mA; f _T =13.5ΓΓu	SOT346,SC59	20000000
W1	BAT54C	PHIL	shd×2	V _R <30 B; I _F <200 мA; V _F (I _F =30 мA)<500 мB; C _D <10 пФ; t _{RR} <5 нс	SOT23,SOD23	
U1	BCX19	ALLEG	non	V _{CB0} =50B; I _{CB0} <100 HA; h ₂₁ =100600; V _{CE(set)} <0.62B	SOT23,SOD23	
U1	BCX19	CDIL	non	V _{CBD} =45B; I _C =500 mA; P _D =250 mBτ; N ₂₁ =100600; f _T >100 MΓц	SOT23,SOD23	
U1	BCX19	ZETEX	non	V _{CB0} =50 B; I _C =500 mA; P _D =330 mBr; h ₂₁ =100600; f _T >200 MΓ _Q	SOT23,SOD23	
U1	BCX19	MOT	non	V _{CR0} =50 B; I _C =500 mA; P _D =330 mB; h ₂₁ =100600; f _T >200 MFu	SOT23,SOD23	
U1p	BCX19	PHIL	non	V _{CB0} =45B; I _C =500 mA; P _D =250 mBr; h ₂₁ =100600; f ₇ > 100 MF _U	SOT23,50D23	70.000
U1t	BCX19	PHIL	non	V _{CB0} =45B; I _C =500 MA; P _D =250 MB; H ₂₁ =100500; I _T >100 MFц	SOT23,SOD23	
UIT U2	BCX20		1	000		16.760.30
		ALLEG	npn	V _{CB0} =30B; I _{CB0} <100 нA; h ₂₁ =100600; V _{CE(sit)} <0.62B	SOT23,SOD23	
U2	BCX20	ZETEX	npn	V _{CBO} =30 B; I _C =500 мA; P _D =330 мBτ; h ₂₁ =100600; f _T >200 MΓu	SOT23,SOD23	
J2	BCX20	CDIL	npn	V _{CB0} =25B;I _C =500 mA;P _D =250 mBr;h ₂₁ =100600;f ₇ >100 MFu	SOT23,SOD23	200000000000000000000000000000000000000
U2p	BCX20	PHIL	npn	V_{CB0} =25B; I_C =500 mA; P_D =250 mBT; h_{21} =100600; f_T >100 M Γ_{II}	SOT23,SOD23	100000000000000000000000000000000000000
U2t	BCX20	PHIL	npn	V_{CB0} =25B; I_C =500 mA; P_D =250 mBT; h_{21} =100600; f_T >100 MFu	SOT23,SOD23	12120112
U3	BSS64	FAIR	non	V_{CB0} = 120 B; I_C = 200 mA; P_D = 350 mBT; h_{21} > 20; f_T > 60 MFц	SOT23,SOD23	B·E·C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
U35	BSR19	CDIL	npn	V _{CB0} =160 B; I _C =600 mA; P _D =250 mBT; h ₂₁ >60; f ₇ =300	SOT23,SOD23	B-E-C
U35	BSR19	PHIL	npn	V_{CB0} =160 B; I_C =600 mA; P_D =250 mBT; h_{21} >60; f_T =300	SOT23,SOD23	B-E-C
U36	BSR19A	CDIL	npn	V _{GB0} =180 B; I _C =600 mA; P _D =250 mBt; h ₂₁ >80; f _T =300	SOT23,SOD23	B-E-C
U36	BSR19A	PHIL	npn	V _{CB0} =180 B; I _C =600 mA; P _D =250 mBT; h ₂₁ >80; f _T =300	SOT23,SOD23	B-E-C
U4	BCX19R	ZETEX	npn	V _{GB0} =50 B; I _C =500 мА; P _D =330 мВт; h ₂₁ =100600; f _T >200 МГц	SOT23,SOD23	B-E-C
U4	BCX19R	PHIL	npn	V _{GB0} =45 B; I _C =500 мА; P _D =250 мВт; h ₂₁ =100600; f _T >100 МГц	SOT23,SOD23	C·B·E
U5	BCX20R	ZETEX	npn	V _{сво} =30 B; I _C =500 мА; P _D =330 мВт; h ₂₁ =100600; f _T >200 МГц	SOT23,SOD23	B·E·C
U5	BCX20R	PHIL	non	V _{GB0} =25 B; I _C =500 мА; P _D =250 мВт; h ₂₁ =100600; f _T >100 МГц	SOT23,SOD23	C·B·E
U6	BSS64R	FAIR		V _{GB0} =120 B; I _G =200 мА; P _D =350 мВт; h ₂₁ >20; f _T >60 МГц	SOT23,SOD23	E-B-C
U7	BSR13	CDIL	ngn	V _{GB0} =60 B;I _G =800 mA; P _D =250 mBT; h ₂₁ =100300; f _T >250 MFu	SOT23,SOD23	
U7	BSR13	SGS	npn	V _{GB0} =60 B; I _G =800 mA; P _D =250 mBT; h ₂₁ =100300; f _T >250 MFu	SOT23,SOD23	
U71	BSR13R	SGS	npn	V _{GB0} =60 B; I _C =800 мА; P _D =250 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	177717700000
U7p	BSR13	PHIL	npn	V _{CP0} =60 B; I _C =800 мА; P _D =250 мВт; h ₂₁ =100300; f _T >250 МГц	SOT23,SOD23	
U7t	BSP13	PHIL	npn	V _{CB0} =60 B; I _C =800 mA; P _D =250 mB; h ₂₁ =100300; f _T >250 MFu	SOT23,SOD23	USON/A DA
U8	BSR14	CDIL	ngn	V _{CR0} =75 B; I _C =800 mA; P _D =250 mBT; h ₂₁ =100300; f _T >300 MFu	SOT23,SOD23	
U8	BSR14	SGS	npn	V _{CR0} =75 B; I _C =800 mA; P _D =250 mBr; h ₂₁ =100300; f _T >300 MFu	SOT23,SOD23	
U81	BSR14R	SGS	npn	V _{CB0} =75 B; I _C =800 mA; P _D =250 mBr; h ₂₁ =100300; f _T >300 MFu	SOT23,SOD23	
U8o	BSR14	PHIL	npn	V _{CB0} =75 B; I _C =800 mA; P _D =250 mBr; h ₂₁ =100300; f _T >300 MFu	SOT23,SOD23	200000000000000000000000000000000000000
U8t	BSR14	PHIL	nan	V _{CB0} =75 B; I _C =800 mA; P _D =250 mBr; h ₂₁ =100300; f _T >300 MFu	SOT23,SOD23	100705344720
U92	BSR17A	CDIL	npn	V _{CB0} =60 B; I _C =200 мА; P _D =250 мВ; h ₂₁ =100300; f _T >300 МГц	SOT23,SOD23	TOUT OF
U92	BSR17A	FAIR	non	V _{CB0} =60 B; I _C =200 mA; P _D =350 mBr; h ₂₁ =100300; f _T >300 MF _Q	SOT23,SOD23	13232 32
U920	BSR17A	PHIL	npn	V _{CB0} =60 B; I _C =200 MA; P _D =350 MB; I _{R2} =100300; I _T >300 MI _L	SOT23,SOD23	12 2
U9 ₀	BSR17	PHIL	onp	V _{GB0} =60 B, I _C =200 мА; Р _D =425 мВт; h ₂₁ =40; f _T >300 МГц	SOT23,SOD23	
UA	2SB852KA	ROHM		V _{CBO} =40 B; I _C =300 мА; P _D =420 мВ; I ₁₂₁ =40, I ₇ >300 мП ц	SOT346,SC59	
UB	2SB852KB	ROHM	pnp	0.50	SOT346,SC59	
UB	2SC5668	NEC	pnp	V _{GB0} =40 B; I _G =300 MA; P _D =200 MBT; h ₂₁ >5000; f _T >200 MFu		
UB UB	NE667M03	NEC	npn	V _{CB0} =15 B;I _C =35 xA; P _D =115 xBr;h ₂₁ =50100;f _T =21 ГГц	SC81,MFPAK SC81,MFPAK	
UC	MSC2404-C	MOT	npn	V _{CB0} =15 B;I _C =35 мА; Р ₀ =115 мВт; h ₂₁ =50100; f _T =21 ГГц		
		_	npn	V _{GB0} =20 B; f ₁ =150 МГц	SOT23,SOD23	
UF	BB801	SIEM	var	V _R <30 B; I _F <50 MA; I _R <0.02 MKA; C _{28B} =0.851.2πΦ; C _{1.B} /C _{28B} =7.89.5	SOT23,SOD23	
UI	2SC4229	REN	npn	V _{CB0} =30 B; I _C =20 mA; P _D =150 mB; h ₂₁ =50180; f _T >700 MFц	SOT346,SC59	100000000
UI	2SC4259	REN	npn	V _{CB0} =30 B; I _C =20 мA; P _O =100 мВт; h ₂₁ =50180; f ₁ >700 МГц	SOT323,SC70	
UV	1SV315	SANYO	pin×2	V _B >50 B; I _F <50 mA; V _F (I _F =50 mA)<1B; I _B <0.1 mrA	SOT323,SC70	
UV	1SV316	SANYO	pin×2	V _R >50 B; I _F <50 mA; V _E (I _F =50 mA)<1B; I _R <0.1 mKA	SOT23,SOD23	
V04	VN45350T	SIL	nMOS	V _{DS} =450B; I _D =20 mA; P _D =800 mBT; R _{DS(on)} <350 Om	SOT23,SOD23	
V1	1SV160	TOSH	var.	$V_R > 15 B; I_R (V_R = 4B) \le 0.1 \text{ MKA}; C_T = 14 \text{ m}$	SOT346,SC59	
V1	DZ23C2V7	VISH	dz×2	V _Z =2.52.9 B;Z _{ZT} (I _Z =5 mA)=83 Om	SOT23,SOD23	
V1	MRF959T1	MOT	npn	V _{CB0} =20 B; I _C =100 мА; P _D =150 мВт; h ₂₁ =75150; f _T =9 ГГц	SOT416,SC75A	
V1	VN50300T	SIL		V _{DS} =500B; I _D =22 mA; P _D =350 mBT; G _F =140 mCm; R _{DS(on)} =25 0m	SOT23,SOD23	
V10	DZ23C6V2	VISH	dz×2	Vz=5.86.6 B; Zzt(Iz=5 mA)=10 Om	SOT23,SOD23	
V11	DZ23C6V8	VISH	dz×2	Vz=6.47.2B;Zzt(Iz=5mA)=80m	SOT23,SOD23	
V12	DZ23C7V5	VISH	dz×2	V _z =7.07.9B;Z _{ZT} (I _Z =5mA)=7Om	SOT23,SOD23	
V13	DZ23C8V2	VISH	dz×2	V _Z =7.78.7B;Z _{ZT} (I _Z =5 MA)=7 OM	SOT23,SOD23	
V13	ZC932	ZETEX	var	V _R <12 B; C ₀ (V _R =2.5 B)=8.510.5 nΦ; C _{2B} /C _{20 B} <3.1; Q>200	SOT23,SOD23	0.0000000000000000000000000000000000000
V14	DZ23C9V1	VISH	dz×2	V _Z =8.59.6B;Z _{ZT} (I _Z =5 мA)=10 Om	SOT23,SOD23	
V14	ZC931	ZETEX	var	$V_B < 12 B; C_D(V_B = 2.5 B) = 6.57.8 \text{ n}\Phi; C_{1B}/C_{4B} = < 3.6; Q > 300$	SOT23,SOD23	
V15	ZC930	ZETEX	var .	$V_R \le 25 \text{ B}; C_D(V_R = 2.5 \text{ B}) = 4.35.5 \text{ n}\Phi; C_{1B}/C_{4B} = \le 3.0; Q \ge 200$	SOT23,SOD23	1513174.387
V15	ZDZ23C10	VISH	dz×2	V _Z =9.410.B, Z _{ZT} (I _Z =5mA)=150m	SOT23,SOD23	
V16	DZ23C11	VISH	dz×2	Vz=10.411.B; Zz1(Iz=5 mA)=20 Om	SOT23,SOD23	A1-A2-K1,K2
V16	ZC934	ZETEX	var	$V_B < 12 B; C_D (V_B = 2.5 B) = 4065 \pi \Phi; C_{1B} / C_{4B} < 3.8; Q > 80$	SOT23,SOD23	A·n.c.·K
V17	DZ23C12	VISH	dz×2	V _Z =11.412.B; Z _{Z1} (I _Z =5 mA)=20 Om	SOT23,SOD23	A1-A2-K1,K2
V17	ZC933	ZETEX	var	$V_R \le 12 B; C_D(V_R = 2.5 B) = 1827 n\Phi; C_{1B}/C_{4B} \le 3.5; Q \ge 150$	SOT23,SOD23	A·n.c.·K
V18	DZ23C13	VISH	dz×2	V ₂ =12.414.B; Z ₇₇ (I ₂ =5 mA)=250m	SOT23,SOD23	A1-A2-K1,K2





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
V19	DZ23C15	VISH	dz×2	Vz=13.815.B; Zz; (Iz=5mA)=30 Om	S0T23,S0D23	A1-A2-K1,K2
V1p	BFT25	PHIL	non	V _{свр} =8B;I _c =6.5 мA; P _D =30 мВт; h ₂₁ >20; f _T =2.3 ГГц	SOT23,SOD23	B·E·C
V2	BFQ67	VIS	npn	V _{CBD} =20 B; I _C =50 MA; P _D =200 MBT; h ₂₁ >65; f _T =8 ITI _L	SOT23, SOD23	B·E·C
V2	DZ23C3V0	VISH	dz×2	Vz=2.83.2B; Zzz(Iz=5 mA)=95 Om	SOT23,SOD23	A1+A2+K1,K2
V2	VN0605T	SIL	nMOS	V _{DS} =60 B;I _D =180 мA; P _D =360 мВт; g _E =80 мСм; R _{DS(cD)} =5 Ом	SOT23, SOD23	G-S-D
V20	DZ23C16	VISH	dz×2	V _z =15.317.B; Z _{zz} (I _z =5mA)=40 Om	SOT23,SOD23	A1-A2-K1,K2
V21	DZ23C18	VISH	dz×2	V ₂ =16.819.B; Z ₂₇ (I ₂ =5 mA)=50 Om	SOT23,SOD23	A1 • A2 • K1. K2
V22	DZ23C20	VISH	dz×2	V ₇ =18.821.B;Z ₇₇ (I ₇ =5 mA)=50 Om	SOT23.SOD23	
V23	DZ23C22	VISH	dz×2	V _Z = 20.823.B; Z _{ZZ} {I _Z = 5 mA} = 55 Om	SOT23.SOD23	
V24	DZ23C24	VISH	dz×2	V _Z =22.825.B; Z _{Z1} (I _Z =5 MA)=80 OM	SOT23,SOD23	-
V25	DZ23C27	VISH	dz×2	Vz=25.128.B; Zzz(Iz=2 мA)=80 Om	SOT23,SOD23	_
V25	PMBT3640	PHIL	pnp	V _{CB0} =12B; I _C =80 MA; P _D =350 MBT; h ₂₁ =30120; f _T >500 MFu	SOT23.SOD23	
V26	DZ23C30	VISH	dz×2	V _Z =2832 B;Z _{Z1} (I _Z =2 MA)=80 OM	SOT23,SOD23	22222222
V27	DZ23C33	VISH	dz×2	V _Z =3135B;Z _Z ((_Z =2mA)=80 Om	SOT23,SOD23	
V28	DZ23C36	VISH	dz×2	V _Z =3438B;Z _{ZY} ((z=2 MA)=90 OM	SOT23,SOD23	
V29	DZ23C39	VISH	dz×2	V _Z =3741B;Z _{ZY} (J=2MA)=90 OM	SOT23,SOD23	
V29 V20	BFQ67	PHIL	non	V _{CB0} =20B;I _C =50 MA;P _D =300 MBT;h ₂₁ >60;f _T =8 ITU,	SOT23,SOD23	
V2p	1SV225	TOSH	var×2			100000000000000000000000000000000000000
V3	DZ23C3V3	VISH	var×2	V _R >32B; I _R (V _R =30B)<0.05 мкA; C _{3B} =18.521 пФ; C _{30B} =6.67.7 пФ	SOT346,SC59 SOT23,SOD23	
V30		10771		Vz=3.13.5B; Zz(Iz=5mA)=950m		
	DZ23C43	VISH	dz×2	Vz=4046B;ZzT(Iz=2MA)=100 OM	SOT23,SOD23	Land Control of the C
V30	DZ23C43	DIODS	dz×2	Vz=4046B;Zzt(lz=2MA)=100 OM	SOT23,SOD23	
V31	DZ23C47	VISH	dz×2	Vz=4450B;ZzT(z=2MA)=100 OM	SOT23,SOD23	
V31	DZ23C47	DIODS	dz×2	V _Z =4450B;Z _{ZT} (I _Z =2 мA)=100 Oм	SOT23,SOD23	
V32	DZ23C51	VISH	dz×2	V _Z =4854B;Z _{ZT} (I _Z =2 мA)=100 Oм	SOT23,SOD23	
V32	DZ23C51	DIODS	dz×2	V _Z =4854B;Z _{ZT} (I _Z =2 мA)=100 Ом	SOT23,SOD23	
V4	1SV228	TOSH	var×2	V _B >15B; I _R (V _B =15B)< 0.01 мкА; С _{3B} =28.532.5 пФ; С _{8B} =11.713.7 пФ	SOT346,SC59	
V4	DZ23C3V6	VISH	dz×2	V _Z =3.43.8 B; Z _{ZT} (I _Z =5 mA)=950m	SOT23,SOD23	-
V5	1SV242	TOSH	var×2	V _B >30 B; I _B (V _B =28 B)< 0.01 мкА; С _{1 B} =3642 пФ; С _{28 B} =2.433 пФ	SOT346,SC59	
V5	DZ23C3V9	VISH	dz×2	Vz=3.74.1 B; Zzt{Iz=5 mA}=95 Om	SOT23,SOD23	
V6	DZ23C4V3	VISH	dz×2	Vz=4.04.6 B; Zzt{Iz=5 mA}=95 Om	SOT23,SOD23	
V7	DZ23C4V7	VISH	dz×2	Vz=4.45.0 B; Zzt{Iz=5 mA}=78 0m	SOT23,SOD23	
V8	DZ23C5V1	VISH	dz×2	Vz=4.85.4B; Zzt(Iz=5 mA)=60 Om	SOT23,SOD23	
V9	DZ23C5V6	VISH	dz×2	Vz=5.26.0 B; Zzt(Iz=5 mA)=40 Om	SOT23,SOD23	A1+A2+K1,K2
VΑ	2SC2776A	REN	npn	V _{CB0} =30 B; I _C =30 мА; P _D =100 мВт; h ₂₁ =3570; f _T =320 МГц	SOT23,SOD23	B·E·C
VB.	2SC2776B	REN	npn	V _{CB0} =30 B; I _C =30 мА; P _D =100 мВт; h ₂₁ =60120; f _T =320 МГц	SOT23,SOD23	B·E·C
VB .	MSC2295-B	MOT	npn	V _{C80} =20 B; I _C =30 мA; P _D =200 мВт; h ₂₁ =70140; f _T > 150 МГц	SOT346,SC59	B·E·C
VC	2SC2776C	REN	npn	V _{CB0} =30B; I _C =30 мA; P _D =100 мВт; h ₂₁ =100200; f _T =320 МГц	SOT23,SOD23	B·E·C
VC	MSC2295-C	MOT	npn	V _{CB0} =20 B; I _C =30 мA; P _D =200 мВт; h ₂₁ =110220; f _T >150 МГц	SOT346,SC59	B·E·C
VO	VP0610T	SIL	pMOS	V _{DS} =60 B;I _D =120 мА; P _D =360 мВт; g _F =70 мСм; R _{DS(on)} =10 Ом	SOT23,SOD23	G·S·D
W01	PDTA143ET	PHIL	Dpnp	V _{CB0} =50B; I _C =100 мA; P _D =250 мВт; h ₂₁ >30; 4.7 кОм/4.7 кОм	SOT23,SOD23	B·E·C
W01	PDTA143EU	PHIL	Dpnp	V _{CB0} =50B; I _C =100 мA; P _D =250 мВт; h ₂₁ >30; 4.7 кОм/4.7 кОм	S0T323,SC70	
W02	PDTC143ET	PHIL	Dnpn	V _{CB0} =50B; I _C =100 мА; P _D =250 мВт; h ₂₁ >30; 4.7 кОм/4.7 кОм	SOT23,SOD23	B·E·C
W02	PDTC143EU	PHIL	Dnpn	V _{CBD} =50 B; I _C =100 мА; P _D =250 мВт; h _{Pl} >30; 4.7 кОм/4.7 кОм	SOT323,SC70	B·E·C
W05	PDTA124ET	PHIL	Dpnp	V _{CB0} =50B; I _C =100 mA; P _D =250 mBT; h ₂₁ >60; 22 kOm/22 kOm	SOT23,SOD23	
W05	PDTA124EU	PHIL	Dono	V _{CR0} =50B; I _C =100 mA; P _D =250 mBT; h ₂₁ >60; 22 kOm/22 kOm	SOT323,SC70	100,003000
W06	PDTC124EU	PHIL	Dnpn	V _{CB0} =50B;I _C =100 mA;P ₀ =250 mBT;h ₂₁ >60;22 kOm/22 kOm	SOT323,SC70	10.762
W06	PMSS3906	PHIL	onp	V _{CBO} =40B; I _C =200 мА; P _D =200 мВт; h ₂₁ =100300; f _T >150 МГц	S0T323,SC70	15
W07	PDTA144ET	PHIL	Dono	V _{CR0} =50B; I _C =100 mA; P _D =250 mBT; h ₂₁ >80;47 кOm/47 кOm	SOT23,SOD23	
W07	PDTA144EU	PHIL	Dono	V _{CB0} =50B; I _C =100 MA; P _D =250 MBT; h ₂₁ >80; 47 KOM/47 KOM	S0T323,SC70	
W08	PDTC144ET	PHIL	Dnpn	V _{CB0} =50B; I _C =100 mA; P _D =250 mB; H ₂₁ >80; 47 KOM/47 KOM	SOT23,SOD23	
	PDTC144EU	PHIL	Dnpn	V _{CB0} =50B; I _C =100 MA; P _D =250 MB; I ₁₂ +260; 47 KOM/47 KOM V _{CB0} =50B; I _C =100 MA; P _D =250 MB; I ₁₂ +80; 47 KOM/47 KOM	S0T323,SC70	100000000000000000000000000000000000000
W08						

SOT490 TESM VMT3 1 SOT523 SOT323 SOT23-3 1 SOT523 SOT324 SOD23-3 1 SOT523 SOT346 SOD23-3 1 SOT523 SOT523 SOT525 SO

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
W10	CMPZDA27V	CSI	dz×2	V _Z (I _{ZT} =2mA)=2529 B; I _L (V _R =18.9 B) < 0.05 m; A; Z _{ZT} (I _{ZT} =2.0 mA) < 80 Om; I _{ZM} =6.2 mA	SOT23,SOD23	K2 · K1 · A2,A1
W11	CMPZDA30V	CSI	dz×2	$V_2(I_{ZT} = 2.0 \text{ mA}) = 2832 \text{ B}; I_2(V_R = 21.0 \text{ B}) \le 0.05 \text{ m/cA}; Z_{ZT}(I_{ZT} = 2.0 \text{ mA}) \le 80 \text{ Om}; I_{ZM} = 5.6 \text{ mA}$	SOT23,SOD23	K2•K1•A2,A1
N11	PDTA114TT	PHIL	Dpnp	V _{CB0} =50 B; I _C =100 мА; P _D =200 мВт; h ₂₁ >200; R ₁ 10 кОм	SOT23,SOD23	B-E-C
₩12	CMPZDA33V	CSI	dz×2	$V_Z(I_{ZT}=2.0 \text{ mA})=3135B; I_Z(V_R=23.1B) \le 0.05 \text{ nicA}; Z_{ZT}(I_{ZT}=2.0 \text{ mA}) \le 80 \text{ Om}; I_{ZM}=5.0 \text{ mA}$	SOT23,SOD23	K2•K1•A2,A1
W12	PDTC114TT	PHIL	Dnpn	V _{CB0} =50 B; I _C = 100 мА; P _D =200 мВт; h ₂₁ >200; R ₁ 10 кОм	SOT23,SOD23	B·E·C
v13	BB207	PHIL	var×2	V _R >15 B; I _R (V _R =15 B)<0.01 мкА; С _{1 B} =7686 пФ; С _{7.5B} =25.529.7 пФ	SOT23,SOD23	A1+A2+K1,K
N13	CMPZDA36V	CSI	dz×2	V ₂ =36 B(5%); P ₀ <350 MBT	SOT23,SOD23	K2 · K1 · A2 A
N14	CMPZDA39V	CSI	dz×2	V ₂ =39 B(5%); P ₀ <350 mBT	SOT23,SOD23	K2 · K1 · A2 A
N15	CMPZDA43V	CSI	dz×2	V _Z =43 B(5%); P _D <350 mBT	SOT23,SOD23	K2·K1·A2,A
N16	CMPZDA47V	CSI	dz×2	V ₂ =47 B(5%); P _D <350 MBT	SOT23,SOD23	K2 · K1 · A2, A
N16	PDTC114ET	PHIL	Dnpn	V _{CB0} =50 B; I _C =50 mA; P _D =250 mBt; h ₂₁ > 30; 10 kOm/10 kOm	SOT23,SOD23	B-E-C
N17	PDTC124ET	PHIL	Dnpn	V _{GR0} =50 B; I _G =100 mA; P _D =250 mBt; h ₂₁ >60; 22 kOm/22 kOm	SOT23,SOD23	B-E-C
N18	PDTC143ZT	PHIL	Dnpn	V _{GB0} =50 B; I _G =100 mA; P _D =250 mBT; h ₂₁ >100; 4.7 kOm/47 kOm	SOT23.SOD23	B-E-C
N19	PDTA143ZT	PHIL	Donp	V _{CR0} =50 B; I _C =100 mA; P _D =250 mBT; h ₂₁ >100; 4.7 kOm/47 kOm	SOT23,SOD23	B-E-C
N1B	PMBT2222	PHIL	npn	V _{CR0} =60 B; I _C =600 MA; P _D =250 MBT; h ₂₁ =100300; f _T >250 MFц	SOT23,SOD23	
N1J	PMBT2369	PHIL	non	V _{CR0} =40 B; I _C =500 MA; P _D =250 MBT; h ₂₁ =40120	SOT23.SOD23	B-E-C
N1P	PMBT2222A	PHIL	npn	V _{GB0} =75 B; I _G =600 мA; P _D =250 мВт; h ₂₁ =100300; f _T >300 МГц	SOT23,SOD23	B-E-C
W1s	BFT92	SIEM	ono	V _{DR0} =20 B; I _D =25 mA; P _D =200 mBt; h ₂₁ > 20; f _T =5000 MFu	SOT23.SOD23	
N1s	BFT92W	SIEM	ono	V _{GR0} =20 B; I _G =25 mA; P _D =200 mBr; h ₂₁ > 15; f _T > 5000 MFu	SOT323,SC70	B+E+C
N23	PDTA114TU	PHIL	Dono	V _{GB0} =50 B; I _G =100 mA; P _D =200 mB1; h ₂₁ >200; R ₁ 10 κOm	SOT323.SC70	
N24	PDTC114TU	PHIL	Dnon	V _{DB0} =50 B; I _C =100 MA; P _D =200 MB;; h ₂₁ >200; R ₁ 10 kOM	SOT323.SC70	
N27	PDTC114YT	PHIL	Dnpn	V _{CB0} :50 B; I _C : 100 mA; P _D :200 mBr; h ₂₁ >100; 10 kOm/47 kOm	SOT23,SOD23	
N29	PDTA114YT	PHIL	Dono	V _{CR0.7} 50 B; I _C : 100 MA; P _D : 200 MB; h ₂ :> 100; 10 KOM/47 KOM	SOT23,SOD23	_
W2F	PMBT2907A	PHIL	ono	V _{CB0} =60 B; I _C =600 мА; P _D =250 мВт; h ₂₁ >50; f _T >200 МГц	SOT23,SOD23	
W3	BZX84-C2V4	PHIL	dz	V _Z (I _{ZT} =5.0 mA)=2.22.6B; I _L (V _R =1.0 B) < 50 mA; Z _{ZT} (I _{ZT} =5.0 mA) < 100 Om; I _{ZM} =200 mA	SOT23,SOD23	
W30	PDTC114YU	PHIL	Dnpn	V _{CR0} =50 B; I _C = 100 mA; P _D =200 mBT; h ₂₁ > 100; 10 kOm/47 kOm	SOT323,SC70	B-E-C
W31	PDTA143XT	PHIL	Dono	V _{GB0} =50 B; I _G =100 мА; P _D =250 мВт; h ₂₁ >50; 4.7 кОм/10 кОм	SOT23,SOD23	B-E-C
N32	PDTC143XT	PHIL	Dnon	V _{CR0} =50 B; I _C =100 MA; P _D =250 MB1; h ₂₁ >50; 4.7 KOM/10 KOM	SOT23.SOD23	
N46	PDTA143XU	PHIL	Dono	V _{GB0} =50 B; I _G =100 mA; P _D =250 mB1; h ₂₁ >50; 4.7 кOm/10 кOm	SOT323.SC70	B-E-C
N47	PDTA143ZU	PHIL	Dono	V _{GR0} =50 B; I _G = 100 mA; P _D =250 mBT; h ₂₁ >100; 4.7 кOm/47 кOm	SOT323.SC70	
N5	BZX84-C3V0	PHIL	dz	V ₂ (I ₂₇ =5.0 mA)=2.83.2B; Z ₂₇ (I ₂₇ =5.0 mA)<100 Om	SOT23.SOD23	
N52	S852TW	VISH	non	V _{GB0} =12 B; I _G =8 мА; P ₀ =30 мВт; h ₂₁ =40150; f ₁ =5.2 ГГц	SOT323.SC70	
N53	PDTC143XU	PHIL	Dnon	V _{CRD} =50 B; I _C =100 mA; P _D =250 mBT; h ₂₁ >50; 4.7 кOm/10 кOm	SOT323,SC70	
N54	PDTC143ZU	PHIL	Dnon	V _{CB0} *50 B; I _C * 100 мА; P _D *250 мВт; h ₂₁ >100; 4.7 кОм/47 кОм	SOT323.SC70	
N55	PDTA114YU	PHIL	Dono	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBr; h ₂₁ >100; 10 κOm/47 κOm	SOT323,SC70	75.077
N6	BZX84C3V3	CSI	dz	V ₂ (I _{ZT} =5mA)=3.13.5B; I ₁ (V _R =1.0B)<5.0 m; A; Z _{ZT} (I _{ZT} =5mA)<95 Om; I _{ZM} <76 MA	SOT23,SOD23	100000000000000000000000000000000000000
W6	BZX84-C3V3	PHIL	dz	V _Z (I _{ZT} =5mA)=3.13.5B;Z _{ZT} (I _{ZT} =5mA)<95 Om	SOT23,SOD23	A·n.c.·K
W 7	BZX84C3V6	CSI	dz	$V_{Z}(I_{ZT}=5mA)=3.43.8B,I_{L}(V_{R}=1.0B)<5.0$ mkA, $Z_{ZT}(I_{ZT}=5mA)<90$ Om; $I_{ZM}<69$ mA	SOT23,SOD23	A·n.c.·K
N7	BZX84-C3V6	PHIL	dz	V ₂ (I _{ZT} =5mA)=3.43.8B;Z _{ZT} (I _{ZT} =5mA)<95 Om	SOT23,SOD23	A·n.c.·K
N74	BAW74	ZETEX	di×2	$V_{\rm R}$ < 50 B; $I_{\rm F}$ < 150 mA; $V_{\rm F}$ ($I_{\rm F}$ = 100 mA) < 1.0 B; $I_{\rm R}$ < 0.1 mkA; $C_{\rm D}$ < 2.0 n Φ ; $I_{\rm RR}$ < 4 Hz.	SOT23,SOD23	A1+A2+K1,K2
N7Y	PDTB123YT	PHIL	Dpnp	V _{GB0} =50 B; I _G =500 мA; P _D =250 мВт; h ₂₁ >70; 2.2 кОм/10 кОм	SOT23,SOD23	B-E-C
8W	BZX84C3V9	CSI	dz	$V_2(I_{ZT}=5\text{ mA})=3.74.1\text{ B}; I_1(V_R=1.0\text{ B})<3.0\text{ mrA}; Z_{ZT}(I_{ZT}=5\text{ mA})<90\text{ Om}; I_{ZM}<64\text{ mA}$	SOT23,SOD23	120020000
W8	BZX84-C3V9	PHIL	dz	V _Z (I _{ZT} =5mA)=3.74.1B;Z _{ZT} (I _{ZT} =5mA)<90 Om	SOT23,SOD23	A·n.c.·K
W 9	BZX84C4V3	CSI	dz	$V_2(I_{2T}=5mA)=4.04.6B;I_1(V_{R}=1.0B) \le 3.0 \text{ m/s}, Z_{ZT}(I_{ZT}=5mA) \le 90 \text{ Om}; I_{ZM} \le 58 \text{ mA}$	SOT23,SOD23	
N 9	BZX84C4V3LT1	MOT	dz	V ₂ (I ₂₇ =5mA)=4.04.6B;Z ₂₇ (I ₂₇ =5mA)<90 Om	SOT23,SOD23	A·n.c.·K





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
W9A	PLVA650A	PHIL	dz	$V_Z(I_{ZT} = 250 \text{ m/sA}) = 4.85.2 \text{ B; } I_L(V_R = 0.8 \text{ fV}_Z) \le 20 \text{ m/sA}; $ $Z_{ZT}(I_{ZT} = 250 \text{ m/sA}) \le 700 \text{ Om; } I_{ZM} = 250 \text{ m/sA}$	SOT23,SOD23	A•n.c.•K
W9B	PLVA653A	PHIL	dz	$V_Z(I_{ZT} = 250 \text{ m/sA}) = 5.15.5 \text{ B; } I_z(V_B = 0.8^+V_Z) \le 5 \text{ m/sA};$ $Z_{ZT}(I_{ZT} = 250 \text{ m/sA}) \le 250 \text{ m/s}, I_{ZM} = 250 \text{ m/s}$	SOT23,SOD23	A•n.c.•K
W9C	PLVA656A	PHIL	dz	$V_2(I_{ZT} = 250 \text{ m/sA}) = 5.45.8 \text{ B}, I_2(V_B = 0.8^{\circ}V_2) \le 1 \text{ m/sA}, I_{ZT}(I_{ZT} = 250 \text{ m/sA}) \le 100 \text{ Om}, I_{ZM} = 250 \text{ m/s}$	SOT23,SOD23	A•n.c.•K
W9D	PLVA659A	PHIL	dz	$V_2(I_{ZT} = 250 \text{ NiKA}) = 5.7 6.1 B; I_1(V_B = 0.8^4V_Z) < 500 \text{ HA};$ $I_2(I_{ZT} = 250 \text{ NiKA}) < 100 Om; I_{ZT}(I_{ZT} = 250 \text{ MA})$	S0T23,S0D23	A•n.c.•K
W9E	PLVA662A	PHIL	dz	$V_2(I_{ZT} = 250 \text{ nicA}) = 6.06.4 \text{ B}; I_1(V_B = 0.8^{\circ}V_Z) \le 100 \text{ HA}; I_{ZT}(I_{ZT} = 250 \text{ m/A}) \le 100 \text{ Om}; I_{ZM} = 250 \text{ m/A}$	SOT23,SOD23	A•n.c.•K
W9F	PLVA665A	PHIL	dz	$V_2(I_{ZT} = 250 \text{ m/sA}) = 6.3 6.7 \text{ B; } I_1(V_B = 0.8^{+}V_2) < 50 \text{ hA}; $ $Z_{ZT}(I_{ZT} = 250 \text{ m/sA}) < 100 \text{ Om; } I_{ZM} = 250 \text{ mA}$	S0T23,S0D23	A•n.c.•K
W9G	PLVA668A	PHIL	dz	$V_Z(I_{ZT} = 250 \text{ m/sA}) = 6.67.0 \text{ B; } I_z(V_B = 0.8 \text{ fV}_Z) \le 10 \text{ HA}; $ $Z_{ZT}(I_{ZT} = 250 \text{ m/sA}) \le 100 \text{ Om; } I_{ZM} = 250 \text{ mA}$	SOT23,SOD23	Arn.c.rK
WA	2SD1383KA	ROHM	npn	V _{CB0} =40B; I _C =300 mA; P _D =200 mBr; h ₂₁ >1000; f _T >250 MFu	S0T346,SC59	B·E·C
WB	2SD1383KB	ROHM	npn	V _{CB0} =40 B; I _C =300 мА; P _D =200 мВт; h ₂₁ >5000; f _T >250 МГц	SOT346,SC59	B·E·C
WB-	2SC5700	REN	non	V _{CB0} =15B; I _C =50 mA; P _D =80 mBT; h ₂₁ =100170; f _T >10 fTu	SC81,MFPAK	B·E·C
WCs	BCR133	INF	Dnpn	V _{CB0} =50B; I _C =100 мА; P _D =200 мВт; h ₂₁ >30; f _T >130 МГц	SOT23,SOD23	B·E·C
WCs	BCR133F	INF	Dnpn	V _{CBD} =50B; I _C =100 мА; P _D =200 мВт; h ₂₁ >30; f _T =130 МГц	TSFP-3,VESM	B·E·C
WCs	BCR133T	INF	Dnpn	V _{CR0} =50B; I _C =100 мА; P ₀ =200 мВт; h ₂₁ >30; f ₁ =130 МГц	S0T416.SC75A	B·E·C
WCs	BCR133W	INF	Dnon	V _{CR0} =50B; I _C =100 mA; P _D =250 mBT; h ₂₁ >30; f _T =130 MFц	S0T323.SC70	B-E-C
WDs	BCR141	INF	Dnon	V _{CR0} =50B; I _C =100 mA; P _D =200 mBT; h ₂₁ >50; f _T >130 MFµ	SOT23.SOD23	2002000
WDs	BCR141F	INF	Dnon	V _{CR0} =50 B; I _C =100 MA; P _D =200 MBT; h _{Pl} >50; f _T >130 MF _U	TSFP-3.VESM	200000000000000000000000000000000000000
WDs	BCR141T	INF	Dnon	V _{CR0} =50B; I _C =100 MA; P _D =200 MB; h ₂₁ >50; f _T >130 MΓц	SOT416.SC75A	
WDs	BCR141W	INF	Dnon	V _{CR0} =50 B; I _C =100 MA; P _D =250 MBT; h ₂₁ >50; f _T =130 MΓ _{II}	S0T323,SC70	
WE1	BES17W	TELEE	non	V _{CB0} -25B; I _C -100 MR; P _D -200 MB; N ₂₁ -20150; f ₁ >1000 MFu	SOT323,SC70	
WE2	BFS17AW	TELEF	non	V _{CB0} =25B; I _C =25MA; P _D =200 MB1; I ₁₂₁ =20150; I _T >1000 MFц	SOT323,SC70	
WES	BCR148	INF	Dnon	000 0 0 0	SOT23,SOD23	
WES	BCR148F	INF		V _{CB0} =50B; I _C =70 MA; P _D =200 MBT; h ₂₁ >70; f _T >100 MF _L		
			Dnpn	V _{CB0} =50B; I _C =70 MA; P _D =200 MBT; h ₂₁ >70; f _T >100 MF _U	TSFP-3,VESM	(C) (C) (C)
WEs	BCR148T	INF	Dnpn	V _{CB0} =50 B; I _C =70 MA; P _D =200 MBT; h ₂₁ >70; f _T >100 MFц	SOT416,SC75A	
Wes	BCR148W	INF	Dnpn	V _{GB0} =50 B; I _C =70 мA; P _D =250 мВт; h ₂₁ >70; f _T =100 МГц	S0T323,SC70	
WFs	BCR112	INF	Dnpn	V_{CB0} =50B; I_C =100 mA; P_D =200 mBT; h_{21} >20; f_T >140 M Γ_{IL}	SOT23,SOD23	
WFs	BCR112W	INF	Dnpn	V_{CB0} =50B; I_C =100 mA; P_D =250 mBT; h_{21} >20; f_T >140 M Γ_{IL}	S0T323,SC70	
WGs	BCR116	INF	Dnpn	V_{CB0} =50B; I_C =100 mA; P_D =200 mBT; h_{21} >70; f_T >160 M Γ_{II}	SOT23,SOD23	1,000,000,000
WGs	BCR116W	INF	Dnpn	V_{C80} =50 B; I_C =100 mA; P_0 =250 mBr; h_{21} >70; f_T =160 M Γ_{II}	SOT323,SC70	
WHs	BCR108	INF	Dnpn	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBr; h_{21} >70; f_T >170 M Γ_{IJ}	SOT23,SOD23	B.E.C
WHs	BCR108F	INF	Dnpn	V_{CB0} =50B; I_{C} =100 mA; P_{D} =200 mBT; h_{21} >70; f_{T} >170 M Γ_{LL}	TSFP-3,VESM	B·E·C
WHs	BCR108T	INF	Dnpn	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBr; h_{21} >70; f_T >170 M Γ_{II}	S0T416,SC75A	B·E·C
WHs	BCR108W	INF	Dnpn	V _{CB0} =50 B; I _C =100 мА; P _D =250 мВт; h ₂₁ > 70; f _T =170 МГц	SOT323,SC70	B.E.C
WIs	BCR158	INF	Dpnp	V _{CB0} =50B; I _C =100 мА; P _D =200 мВт; h ₂₁ >70; f _T >200 МГц	SOT23,SOD23	B·E·C
WIs	BCR158F	INF	Dpnp	V _{CB0} =50B; I _C =70 мA; P _D =250 мВт; h ₂₁ >70; f _T =100 МГц	TSFP-3,VESM	B·E·C
WIs	BCR158T	INF	Dpnp	V _{CB0} =50 B; I _C =70 мA; P _D =250 мВт; h ₂₁ >70; f _T =100 МГц	SOT416,SC75A	B·E·C
WIs	BCR158W	INF	Dpnp	V _{CB0} =50B; I _C =100 мА; P ₀ =250 мВт; h ₂₁ >70; f _T =200 МГц	SOT323,SC70	B·E·C
WJs	BCR135	INF	Dnpn	V _{CB0} =50 B; I _C =100 мА; P _D =200 мВт; h ₂₁ > 70; f _T > 150 МГц	SOT23,SOD23	B·E·C
WJs	BCR135F	INF	Dnpn	V _{CBD} =50B; I _C =100 мА; P _D =200 мВт; h ₂₁ >70; f _T >150 МГц	TSFP-3,VESM	B·E·C
WJs	BCR135T	INF	Dnpn	V _{CR0} =50B; I _C =100 мА; P _D =200 мВт; h ₂₁ >70; f _T > 150 МГц	S0T416,SC75A	B·E·C
WJs	BCR135W	INF	Dnon	V _{CR0} =50 B; I _C =100 mA; P _D =250 mBT; h _{Pl} >70; f _T =150 MF _L	S0T323.SC70	
WK-	2SC5907	REN	non	V _{CR0} =15B; I _c =80 MA; P _D =80 MBT; h ₂₁ =120170; f _T >5 ITu		B·E·C
WKs	BCR119	INF	Dnon	V _{CR0} =50B; I _C =100 мA; P _D =200 мВт; h ₂₁ =120630; f ₇ >150 МГц	SOT23.SOD23	100 march 100 mg
WKs	BCR119W	INF	Dnpn	V _{CR0} =50 B; I _C =100 MA; P _D =200 MBT; I _{P2} =120630; f ₇ >150 MΓц	S0T323.SC70	
NL-	2SB1691	REN	pnp	V _{CR0} =60B; I _C =14; P _D =800 MB; I _{D2} =200500; f _T =310 MFq	SOT23,SOD23	
	EUD 1031	PULL	huh	1.C80 -000'1C -1 W'L D -000 MD1'151 -500000'1L -0.10 MH II	00120,00020	D L'U
WLs	BCR146	INF	Dnon	V _{CB0} =50B; I _C =70 MA; P _D =200 MBT; h ₂₁ >50; f _T >150 MFu	SOT23.SOD23	D.E.C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
WMs	BCR183	INF	Dpnp	V_{CB0} =50 B; I_C = 100 mA; P_D =200 mBt; h_{21} >30; f_T >200 MFu	SOT23,SOD23	B-E-C
WMs	BCR183F	INF	Dpnp	V_{CB0} =50 B; I_C = 100 mA; P_D =250 mBt; h_{21} >30;	TSFP-3,VESM	B-E-C
WMs	BCR183T	INF	Dpnp	V_{CB0} =50 B; I_C = 100 mA; P_D =250 mBt; h_{21} >30;	S0T416,SC75A	B-E-C
WMs	BCR183W	INF	Dpnp	V_{CB0} =50 B; I_C = 100 mA; P_D =250 mBt; h_{21} > 30; f_T > 200 MFu.	SOT323,SC70	B-E-C
WNs	BCR185	INF	Dpnp	V _{CB0} =50 B; I _C = 100 мА; P _D =200 мВт; h ₂₁ > 70; f _T > 200 МГц	SOT23,SOD23	B-E-C
WNs	BCR185W	INF	Dpnp	V_{CB0} =50 B; I_C = 100 mA; P_D =250 mBT; h_{21} >70; f_T =200 MF μ	SOT323,SC70	B-E-C
WO4	PMBS3904	PHIL	npn	V _{CB0} =60 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ =100300; f _T > 180 МГц	SOT23,SOD23	B·E·C
W06	PMBS3906	PHIL	pnp	V _{CB0} =40 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ =100300; f _T >150 МГц	SOT23,SOD23	B·E·C
WOs	BCR191	INF	Dpnp	V _{CB0} =50 B; I _C = 100 мА; P _D =200 мВт; h ₂₁ >50; f _T >200 МГц	SOT23,SOD23	B-E-C
WOs	BCR191W	INF	Dpnp	V _{CB0} =50 B; I _C =100 мА; P _D =250 мВт; h ₂₁ >50; f _T >200 МГц	SOT323,SC70	B-E-C
WP2	BFR92A	TELEF	npn	V _{GB0} =20 B; I _G =25 mA; P ₀ =273 mBT; h ₂₁ >40; f _T =4500 MFu,	SOT23,SOD23	B-E-C
WPs	BCR192	INF	Dono	V _{GB0} =50 B; I _G = 100 мА; P _D =250 мВт; h ₂₁ > 70; f _T > 200 МГц	SOT23,SOD23	B·E·C
WPs	BCR192F	INF	Dpnp	V _{CR0} =50 B; I _C = 100 мА; P _D =250 мВт; h ₂₁ >70; f _T >200 МГц	TSFP-3,VESM	B-E-C
WPs	BCR192T	INF	Dono	V _{DB0} =50 B; I _D =100 mA; P _D =250 mBr; h ₂₁ >70; f _T >200 MΓ _{LL}	S0T416,SC75A	B·E·C
WPs	BCR192W	INF	Dono	V _{DB0} =50 B; I _D =100 mA; P _D =250 mBT; h ₂₁ >70; f _T >200 MFu	SOT323,SC70	B-E-C
WR	MSD602R	MOT	npn	V _{GRO} =25 B; I _G = 150 MA	SOT346,SC59	
WR2	BFR93AW	TELEF	non	V _{GB0} =20 B; I _G =50 mA; P _D =300 mBr; h ₂₁ =50200; f ₁ =5500 MFu	SOT323,SC70	B·E·C
WRE	BFR280TW	TELEF	npn	V _{CR0} =10 B; I _C =10 MA; P _D =80 MBT; h _P =30200; f _T =7500 MFu	SOT323,SC70	B-E-C
WRF	BFR181TW	TELEF	nan	V _{CR0} =20 B; I _C =20 mA; P _D =175 mBt; h ₂₁ > 50; f _T =8 FFu	SOT323.SC70	100710344724
WRG	BFR182TW	TELEF	non	V _{GB0} =20 B; I _G =35 MA; P ₀ =250 MBT; h ₂₁ =50200; f _T =8000 MFu	S0T323.SC70	707 0
WPH	BFR183TW	TELEF	non	V _{CB0} =20 B; I _C =65 mA; P ₀ =450 mBr; h ₂₁ =50200; f _T =8000 MFu	S0T323.SC70	3222 28
WRs	BCR198	INF	Dono	V _{CP0} =50 B; I _C =70 мA; P ₀ =200 мВт; h ₂₁ >70; f _T >190 МГц	SOT23,SOD23	
WRs	BCR198W	INF	Donp	V _{CR0} = 50 B; I _C = 70 мА; Р _П = 250 мВт; h ₂₁ > 70; f _T = 190 МГц	SOT323,SC70	
WSs	BCR169	INF	Dono	V _{CPM} =50 B; I _C =100 mA; P _D =200 mBr; h ₂₁ =120630; f _T >200 MFu	SOT23.SOD23	
WSs	BCR169W	INF	Donp	V _{CR0} =50 B; I _C =100 MA; P _D =250 MBr; h ₂₁ =120630; f _T >150 MFu	SOT323,SC70	
WTs	BCR166	INF	Dono	V _{CR0} =50 B; I _C =100 MA; P _D =200 MBT; h ₂₁ >70; f _T >160 MFu	SOT23.SOD23	10000000
WTs	BCR166W	INF	Dono	V _{CR0} =50 B; I _C =100 MA; P _D =250 MBT; h ₂₁ >70; f _T =160 MFu,	SOT323.SC70	T00E 0
WU	BCR162T	INF	Dono	V _{CRII} *50 B; I _C * 100 MA; P _D *200 MBT; h ₂₁ > 20; f _T > 200 MFц	SOT416.SC75A	
WUs	BCR162	INF	Dono	V _{CRN} =50 B; I _C =100 MA; P _D =200 MBT; h ₂₁ >20; f _T >200 MFL	SOT23.SOD23	
WUs	BCR162F	INF	Dono	V _{CR0} =50 B; I _C =100 MA; P _D =200 MBT; h ₂₁ >20; f _T >200 MFu	TSFP-3,VESM	200000000000000000000000000000000000000
WUs	BCR162W	INF	Dono	V _{CB0} =50 B; I _C =100 MA; P _D =250 MB; h ₂ ; >20; f _T >200 MF _L	S0T323,SC70	100000000
WV2	BFQ67W	VIS	non	V _{CB0} =20 B; I _C =50 MA; P _D =200 MB; I _{D2} >25; I _T >250 MI G	SOT323,SC70	1000
WV3	BAT54A	PHIL	shd×2	V _B <30 B; I _E <200 mA; V _E (I _E =30 mA)<500 mB; C _D <10 mΦ; t _{BB} <5 Hc	SOT23,SOD23	1000000 000
WV4	BAT54S	PHIL	shd×2	V _R <30 B; I _F <200 MA; V _F (I _F =30 MA)<500 MB; C _D <10 nΦ; t _{RR} <5 Hc	SOT23,SOD23	
WVs	BCR129	INF	Dnon	V _{CBO} =50 B; I _C =100 мА; Р _D =200 мВ; h ₂₁ =120630; f _T >150 МГц	SOT23,SOD23	
WW1	BAT54C	PHIL	shd×2	V _R <30 B; I _E <200 mA; V _E (I _E =30 mA)<500 mB; C _D <10 πΦ; t _{BR} <5 Hc	SOT23,SOD23	
WW3	CMPZDA2V4	CSI	dz×2	V _Z =2.4 B(5%); P _D <350 мВт	SOT23,SOD23	
WW4	CMPZDA2V7	CSI	dz×2	V _Z =2.7 B(5%); P _D <350 мВт	SOT23,SOD23	NAME OF TAXABLE PARTY.
WW5	CMPZDA3V0	CSI	dz×2	V ₂ =2, P B(5%), P ₀ < 350 MBT V ₂ =3,0 B(5%), P ₀ < 350 MBT	SOT23,SOD23	Control Control
WW6	CMPZDA3V0 CMPZDA3V3	CSI	dz×2	V ₂ =3.3 B(5%); P ₀ <350 MBT	SOT23,SOD23	
WW7	CMPZDA3V3	CSI	dz×2	$V_2(I_{77}=5.0 \text{ mA})=3.43.8 \text{ B; I}_1(V_B=1.0 \text{ B}) \le 2.0 \text{ m/sA}; Z_{77}(I_{77}=5.0 \text{ m/s}) \le 95.0 \text{ m};$	SOT23,SOD23	
				I _{ZM} =45 MA		
WW8	CMPZDA3V9	CSI	dz×2	$V_Z(I_{ZT}$ =5.0 mA)=3.74.1 B; $I_L(V_B$ =1.0 B)<2.0 mxA; $Z_{ZT}(I_{ZT}$ =5.0 mA)<90 0 m; I_{ZM} =43 mA	SOT23,SOD23	K2 K1 A2 A1
WW9	CMPZDA4V3	CSI	dz×2	$V_2(I_{ZT}=5.0 \text{ mA})=4.04.6 \text{ B; } I_2(V_{B}=1.0 \text{ B}) \le 1.0 \text{ m; A; } Z_{ZT}(I_{ZT}=5.0 \text{ mA}) \le 90 \text{ Om; } I_{ZM}=40 \text{ mA}$	SOT23,SOD23	K2 · K1 · A2,A1
WXs	BCR196	INF	Dono	V _{GR0} =50 B; I _G =70 mA; P _D =200 mBt; h ₂₁ > 50; f _T > 150 MFu,	SOT23,SOD23	B·E·C
WXs	BCR196W	INF	Dono	V _{CR0} =50 B; I _C =70 mA; P _D =250 mBt; h ₂₁ >50; f _T =150 MFu	SOT323.SC70	
WZ-	2SC5872	REN	non	V _{CB0} =15 B; I _C =50 мА; P _D =200 мВт; h ₂₁ =90140; f ₁ =10 ГГц	SC81,MFPAK	120000000000000000000000000000000000000
WZs	BCR142	INF	Dnon	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBr; h ₂₁ >70; f _T >150 MFu	SOT23.SOD23	222
WZs	BCR142W	INF	Dnpn	V _{CRN} =50 B; I _C = 100 MA; P _D =250 MBT; h ₂₁ > 70; f _T =150 MFu	SOT323,SC70	
X	2SB1051K	ROHM	ono	V _{CB0} -32 B; I _C -1000 мА; P _D -200 мВт; h ₂₁ -390; f _T > 150 МГц	SOT346.SC59	





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
(1p	BFT93	PHIL	Dpnp	V _{CBO} =15B; I _C =35мA; P _D =300 мВт; h ₂₁ >20; f _T >5500 МГц	SOT23,SOD23	B·E·C
(1s	BFT93	SIEM	Dpnp	V _{CBD} =15B; I _C =35мA; P _D =300 мВт; h ₂₁ >20; f _T >5500МГц	SOT23,SOD23	B·E·C
Κ2	BZX84-C30	ZETEX	dz	V ₂ (I _{2T} =2 MA)=28.032.0B;Z _{2T} (I _{2T} =2 MA)<80 OM	SOT23,SOD23	A·n.c.·K
K 2	BZX99-C13	PHIL	dz	V ₂ (I ₂₇ =50mKA)=12.3513.65B;P _D <300mB	SOT23,SOD23	A+n.c.+K
(3	BZX84-C33	ZETEX	dz	V ₂ (I _{2T} =2 mA)=31.035.0B;Z _{2T} (I _{2T} =2 mA)<80 Om	SOT23,SOD23	A·n.c.·K
X3	BZX99-C15	PHIL	dz	V ₂ (I ₂₇ =50mKA)=14.2515.75B;P _D <300 MB	SOT23,SOD23	A·n.c.·K
X4	BFT93R	SIEM	Dpnp	V _{CR0} =15B; I _C =35 мА; P _D =300 мВт; h ₂₁ >20; f _T >5500 МГц	SOT23,SOD23	C·B·E
X4	BZX84-C36	ZETEX	dz	V ₂ (I _{2T} =2 mA)=33.038.0B;Z _{2T} (I _{2T} =2 mA)<90 Om	SOT23,SOD23	A·n.c.·K
X42	2SK1001	NEC	nFET	V _{DS} =22B; I _D =10 мA; P _D =250 мВт; Q _E >20 мСм; I _{DSS} =1050 мА	SOT23,SOD23	D·S·G
X43	2SK1001	NEC	FET	V _{DS} =22 B; I _D =10 мA; P _D =250 мВт; Q _E >20 мСм; I _{DSS} =1050 мА	SOT23,SOD23	D·S·G
X5	MMBV409LT1	MOT	var	V _B >20 B; I _E =200 mA; C _{3B} =2632 πΦ; C _{3B} /C _{6B} =1.51.9	SOT23,SOD23	A+n.c.+K
X6	2SD1048X6	SANYO	non	V _{CB0} =20 B; I _C =700 мА; P _D =200 мВт; h ₂₁ =200400; f _T =250 МГц	SOT23,SOD23	B·E·C
X6	BZX84-C43	ZETEX	dz	V ₂ (I _{2T} =2 mA)=40.046.0B;Z _{2T} (I _{2T} =2 mA)<1500m	SOT23,SOD23	A+n.c.+K
X7	2SD1048X7	SANYO	non	V _{CBO} =20 B; I _C =700 мА; P _D =200 мВт; h ₂₁ =300600; f _T =250 МГц	SOT23,SOD23	B·E·C
X7	BZX84-C47	ZETEX	dz	V ₂ (I _{2T} =2 mA)=44.050.0B;Z _{2T} (I _{2T} =2 mA)<1700m	SOT23,SOD23	A·n.c.·K
X8	2SD1048X8	SANYO	non	V _{CB0} =20B; I _C =700 mA; P _D =200 mBT; h ₂₁ =450900; f _T =250 MFц	SOT23,SOD23	
X9	1SS398	TOSH	di×2	V _B <400 B; I _E <100 mA; V _E (I _E =100 mA)<1.3B; I _B <1.0 mkA	SOT346,SC59	A1 · K2 · K1,A2
XΑ	BZX99-C4V7	PHIL	dz	V _Z (I _{ZT} =50 mKA)=4.474.94 B; P _D < 300 mBr	SOT23,SOD23	
XΑ	RN1101	TOSH	Dnon	V _{CEO} =50B;I _C =150 mA;P _D =100 mBT;F _T >250 MFu;R ₁ /R ₂ =4.7/4.7 кОм	SOT416,SC75A	The second secon
XA	RN1101F	TOSH	Dnon	V _{CED} *50B;I _C *150 MA;P _D *100 MBT;f _T >250 MFu;R ₁ /R ₂ *4.7/4.7 KOM	SOT490.SC89	10.17.00.1.190
XA	RN1101FT	TOSH	Dnon	V _{CEO} =50B; I _C =150 мА; P _D =100 мВт; f _T >250 МГц; R ₁ /R ₂ =4.7/4.7 кОм	TESM	B·E·C
XA	RN1301	TOSH	Dnon	V _{CEO} =50B;I _C =100 MA;P _D =100 MBT;f _T =250MFu;R ₁ /R ₂ =4.7 KOM/4.7 KOM	SOT323.SC70	
XA	RN1401	TOSH	Dnpn	V _{CF0} =50B;I _C =100 MA;P _D =200 MBT;F _T =200 MFц;R ₁ /R ₂ =4.7/4.7 кОм	SOT346,SC59	
XAs	BCR503	INF	Dnon	V _{CR0} =50B; I _C =500 mA; P _D =330 mBτ; h _{P1} >40; f _T >100 MΓц	SOT23.SOD23	100000000000000000000000000000000000000
XB	2SC4416	REN	non	V _{сво} -25В; I _с -50 мА; Р _о -150 мВг; h ₂₁ -50180; f ₇ -3 ГГц	SOT346,SC59	
XB	BZX99-C5V1	PHIL	dz	V _Z (I _{ZT} =50 mkA)=4.855.36 B;P _D <300 mBT	SOT23,SOD23	100000000000000000000000000000000000000
XB	RN1102	TOSH	Dnon	V _{CF0} *50B;I _C *150 MA;P _D *100 MBT;F _T >250 MFu;R ₁ /R ₂ *10/10 kOm	SOT416,SC75A	100000000000000000000000000000000000000
XB	RN1102F	TOSH	Dnon	V _{CF0} *50B; I _C *150 мА; Р _D *100 мВт; f _T >250 МГц; R ₁ /R ₂ *10/10 кОм	SOT490.SC89	
XB	RN1102FT	TOSH	Dnpn	V _{CEO} ⁻ 50B; I _C ⁻ 150 MA; P _D ⁻ 100 MBT; f _T >250 MFu; R ₁ /R ₂ ⁻ 10/10 KOM	TESM	B·E·C
XB	RN1302	TOSH	Dnon	V _{CF0} -50B;I _C -100 MA;P _D -100 MBT;F _T -250 MFu;R ₁ /R ₂ -10 KOM/10 KOM	SOT323.SC70	
XB	RN1402	TOSH	Dnpn	V _{CEO} -50B;I _C -100 MA;P _D -200 MBT;F _T -200 MTq;R ₁ /R ₂ -10/10 kOM	SOT346,SC59	
XBs	BCR553	INF	Donio	V _{CBO} =500; I _C =500 MA; P _D =330 MBT; h ₂₁ >40; f _T >150 MFц	SOT23.SOD23	1.020.0201.007
XC	BZX99-C5V6	PHIL	dz	V _Z (I _{ZT} =50 mkA)=5.325.88 B; P _D <300 mBT	SOT23,SOD23	
XC	RN1103	TOSH	Dnon	V_{CE0} = 50 B; I_C = 150 mA; P_D = 100 mBT; f_T > 250 MFu; R_1/R_2 = 22/22 kOm	SOT416.SC75A	100000000000000000000000000000000000000
KC .	RN1103F	TOSH	Dnpn	V _{CEO} *50B;I _C *150 MA;P _D *100 MBT;F _T >250 MFu;R ₁ /R ₂ *22/22 KOM	S0T490,SC89	
XC	PN1103FT	TOSH	Dnon	V_{CF0}^{*} 50 B; I_{C}^{*} 150 MA; P_{D}^{*} 100 MBT; f_{T}^{*} 250 MFu; R_{1}/R_{D}^{*} 22/22 KOM	TESM	B·E·C
XC	RN1303	TOSH	Dnon	V _{CEO} *50B;I _C *100 MA;P _D *100 MB;;I _T *220 MFu;R ₁ /R ₂ *22/22 KOM V _{CEO} *50B;I _C *100 MA;P _D *100 MB;;I _T *250 MFu;R ₁ /R ₂ *22 KOM/22 KOM	SOT323.SC70	
XC	PN1403	TOSH	Dnon	V _{CEO} ⁻ 50 B;I _C ⁻ 100 MA;P _D ⁻ 100 MB;;γγ ⁻ 200 MFц;R ₁ /R ₂ -22/22 κOM	SOT346.SC59	Lot to the Williams
XCs	BCR533	INF	Dnon	V _{CB0} =50B; I _C =500 mA; P _D =330 mBr; h ₂₁ >70; f _T >100 MFц	SOT23.SOD23	20000000
XD	BZX99-C6V2	PHIL	dz	V _Z (I _{ZT} =50 MKA)=5.896.51 B; P _D < 300 MB _T	SOT23,SOD23	
XD	RN1104	TOSH	Dnpn	V _{CF0} *50B;I _C *150 MA;P _D *100 MB;;f _T >250 MFu;B ₁ /R ₂ *47/47 KOM	SOT416.SC75A	
XD	RN1104F	TOSH	Dnon	$V_{CF0}^{-5}50B_1I_C^{-1}50MA_1P_0^{-1}100MB_1, f_7>250MFu_1R_1/R_2-47/47 KOM$	SOT490.SC89	
XD	PN1104FT	TOSH	Dnpn	V _{CEO} =50B;I _C =150 MA;P _D =100 MBT;I _T >250 MFu;R ₁ /R ₂ =47/47 KOM	TESM	B·E·C
XD	RN1304	TOSH	Dnpn	V _{CEO} *50B;I _C *100 MA;P _D *100 MB;;I _T *250 MFu;R ₁ /R ₂ *47/47 KOM V _{CEO} *50B;I _C *100 MA;P _D *100 MB;;I _T *250 MFu;R ₁ /R ₂ *47 KOM/47 KOM	SOT323,SC70	
XD	RN1404	TOSH	Dnpn	V _{CEO} -50B;I _C =100 MA;P _D =100 MB;;T _T =200 MFц;R ₁ /R ₂ =47 κOM V _{CEO} -50B;I _C =100 MA;P _D =200 MB;;T _T =200 MFц;R ₁ /R ₂ =47/47 κOM	SOT346.SC59	1000000000
XDs	BCR555	INF	Dono	V _{CBO} =50B,I _C =100 MA; P _D =200 MB; I _T =200 MI ц, R ₁ /n ₂ =47/47 КОМ V _{CBO} =50B; I _C =500 MA; P _D =330 мBт; I ₂₁ >70; f ₁ >150 МГц	SOT23.SOD23	
XE	BCH000 BZX99-C6V8	PHIL	dz dz	V _{CB0} =50B; I _C =500 MA; Р _D =330 MBT; П ₂₁ > 70; Т ₁ > 150 МПЦ V _Z (I _{ZT} =50 MKA)=6.467.14 B; Р _D < 300 мВт	SOT23,SOD23	12-30-10
XE	RN1105	TOSH	Dnon	V _{2f(2T} =50MKA)=6.467.14 B; P ₀ < 300 MB1 V _{CE0} =50B; I _C =150 MA; P _D =100 MB1; I _T > 250 MFu; R ₁ /R ₂ =2.2/47 KOM	SOT416.SC75A	
KE KE	RN1105 RN1105F	TOSH	Dnpn		SOT490,SC89	
KE KE	RN1105FT	TOSH	_	V _{CEO} *50B;I _C *150 MA;P _O *100 MB;;f _T >250 MFu;R ₁ /R ₂ *2 2/47 KOM	TESM	B-E-C
XE	RN1305	TOSH	Dnpn	V _{CE0} =50B;I _C =150 MA;P _D =100 MB;;f _T >250 MFu;R ₁ /R ₂ =2.2/47 KOM	(
	DESIGN LISTED	HUSH	Dnpn	V _{CF0} =50 B;I _C =100 MA;P _D =100 MBT;I _T =250 MFц;R ₁ /R ₂ =2.2 kOm/47 kOm	SOT323,SC70	D.C.C

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
KF	2SC4464	REN	npn	V _{GB0} =15 B; I _G =5 мА; Р _D =50 мВт; h ₂₁ =40250; f _T >2.5 ГГц	SOT323,SC70	B-E-C
(F	RN1106	TOSH	Dnpn	V _{CFD} =50 B; I _C =150 mA; P _D =100 mB _T ; f _T >250 MFu; R ₁ /R ₂ =4.7/47 кОм	SOT416,SC75A	B-E-C
ΧF	RN1106F	TOSH	Dnpn	V _{CF0} =50 B; I _C =150 mA; P _D =100 mB _T ; f _T >250 MFu; R ₁ /R ₂ =4.7/47 кОм	SOT490,SC89	
KF	RN1106FT	TOSH	Dnpn	V _{CEO} =50B; I _C =150 мA; P _O =100 мВт; f _T >250 МГц; R ₁ /R ₂ =4.7/47 кОм	TESM	B-E-C
KF	RN1306	TOSH	Dnpn	V _{CEO} =50 B; I _C =100 мA; P _O =100 мВт; f _T =250 МГц; R ₁ /R ₂ =4.7 кОм/47 кОм	SOT323,SC70	B-E-C
KF	RN1406	TOSH	Dnpn	V _{CF0} =50 B; I _C =100 mA; P _D =200 mBT; f _T =200 MFu; R ₁ /R ₂ =4.7/47 kOm	SOT346,SC59	100000000000000000000000000000000000000
XFs	BCR512	INF	Dnpn	V _{сво} =50 B; I _C =500 мА; P _D =330 мВт; h ₂₁ >60; I _T >100 МГц	SOT23,SOD23	B-E-C
KGs	BCR523	INF	Dnpn	V _{GB0} =50 B; I _C =500 мА; P _D =330 мВт; h ₂₁ >70; f _T >100 МГц	SOT23,SOD23	B-E-C
(H	RN1107	TOSH	Dnpn	V _{CF0} =50 B; I _C =150 mA; P _D =100 mBT; F _T >250 MFu; R ₁ /R ₂ =10/47 kOm	SOT416,SC75A	
(H	RN1107F	TOSH	Dnpn	V _{CF0} =50 B; I _C =150 mA; P _D =100 mBr; f _T >250 MFu; R ₁ /R ₂ =10/47 kOm	SOT490.SC89	
(H	RN1107FT	TOSH	Dnpn	V _{CEO} =50 B; I _C =150 mA; P _O =100 mBT; f _T >250 MFu; R ₁ /R ₂ =10/47 κOm	TESM	B-E-C
(H	RN1307	TOSH	Dnon	V _{CED} =50 B; I _C =100 мА; P _D =100 мВт; f _T =250 МГц; R ₁ /R ₂ =10 кОм/47 кОм	SOT323.SC70	1270320000
(H	RN1407	TOSH	Dnpn	V _{CF0} =50 B; I _C =100 mA; P _D =200 mB _T ; f _T =200 MFu; R ₁ /R ₂ =10/47 κOm	SOT346.SC59	
(Hs	BCR573	INF	Dono	V _{CB0} =50 B; I _C =500 MA; P _D =330 MBT; h ₂₁ >70; f _T >150 MFu	SOT23.SOD23	90077 52
d	RN1108	TOSH	Dnpn	V _{CF0} =50 B; I _C =150 mA; P _D =100 mBT; f _T >250 MFu; R ₁ /R ₂ =22/47 кОм	SOT416,SC75A	100,000
ď	RN1108F	TOSH	Dnpn	V _{CF0} =50 B; I _C =150 мА; P _D =100 мВт; f _T >250 МГц; R ₁ /R ₂ =22/47 кОм	SOT490,SC89	
ď	RN1108FT	TOSH	Dnpn	V_{CEO}^{-50B} , I_C^{-150MA} , $P_O^{-100MBT}$, $I_T^{-250MBT}$, I_T^{-150MA} , $P_O^{-100MBT}$, $I_T^{-150MBT}$, $I_T^{-150MBT}$, $I_T^{-150MBT}$, $I_T^{-150MBT}$	TESM	B·E·C
d a	RN1308	TOSH	Dnon	V _{CED} =50 B; I _C =100 MA; P _D =100 MB; I _T =250 MFu; R ₁ /R ₂ =22 KOM/47 KOM	SOT323.SC70	
d O	RN1408	TOSH	Dnpn	V _{CED} =50 B; I _C =100 MA; P _D =100 MB1; I _T =250 MFu; R ₁ /R ₂ =22 kGM/47 kGM V _{CED} =50 B; I _C =100 MA; P _D =200 MB1; FT200 MFu; R ₁ /R ₂ =22/47 kGM	SOT346.SC59	T00570070
u U	RN1109	TOSH	Dnpn	V _{CED} =50 B; I _C =100 MA; P _D =200 MBT; T1200 MI II; H ₁ /H ₂ =22/47 KOM V _{CED} =50 B; I _C =150 MA; P _D =100 MBT; f _T >250 MFI _I ; R ₁ /R ₂ =47/22 kOM	SOT416.SC75A	
W W	RN1109F	TOSH				
(J			Dnpn	V _{CED} =50 B; I _C =150 mA; P _D =100 mBr; f _T >250 MFu; B ₁ /R ₂ =47/22 kOM	S0T490,SC89	
	RN1109FT	TOSH	Dnpn	V _{GED} =50 B; I _G =150 мA; P _D =100 мВт; f _T >250 МГц; R ₁ /R ₂ =47/22 кОм	TESM	B·E·C
(J	RN1309	TOSH	Dnpn	V _{CEO} = 50 B; I _C = 100 мА; P _D = 100 мВт; f _T = 250 МГц; R ₁ /R ₂ = 47 кОм/22 кОм	S0T323,SC70	
U	RN1409	TOSH	Dnpn	$V_{CEO} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; f_T = 200 \text{ MFL}; R_1/R_2 = 47/22 \text{ kOm}$	SOT346,SC59	
(K	RN1110	TOSH	Dnpn	$V_{\text{CEO}} = 50 \text{ B; } I_{\text{C}} = 150 \text{ mA; } P_{\text{D}} = 100 \text{ mBr; } f_{\text{T}} > 250 \text{ MFu; } R_{\text{1}} = 4.7 \text{ kOm}$	SOT416,SC75A	100000000000000000000000000000000000000
(K	RN1110F	TOSH	Dnpn	$V_{CED} = 50 \text{ B; } I_C = 150 \text{ mA; } P_D = 100 \text{ mBT; } f_T > 250 \text{ MFu; } R_1 = 4.7 \text{ kOm}$	SOT490,SC89	777 5
(K	RN1110FT	TOSH	Dnpn	V_{CEO} =50 B; I_C =150 mA; P_D =100 mBT; f_T >250 MFц; R_1 =4.7 кOm	TESM	B-E-C
(K	RN1310	TOSH	Dnpn	V _{CED} = 50 B; I _C = 100 мА; P _D = 100 мВт; f _T = 250 МГц; R ₁ = 4.7 кОм	S0T323,SC70	
(K	RN1410	TOSH	Dnpn	V _{CED} =50 B; I _C =100 mA; P _D =200 mBt; f _T =200 MFц; R ₁ =4.7 кОм	SOT346,SC59	
(Ks	BCR519	INF	Dnpn	V _{CB0} =50 B; I _C =500 мA; P _D =330 мВт; h ₂₁ =120630; f _T >100 МГц	SOT23,SOD23	
(L	BZX99-C2V4	PHIL	dz	V _Z (I _{ZT} =50 mKA)=2.282.52B;P _O <300 mBt	SOT23,SOD23	1000 0 EC 2000 0 ES
Ls	BCR569	INF	Dpnp	V_{CB0} =50 B; I_C =500 mA; P_D =330 mBT; h_{21} =120630; f_T >150 M Γ_{II}	SOT23,SOD23	70.7
M	2SC4591	REN	npn	V _{GB0} =15 B; I _C =50 мА; Р _D =150 мВт; h ₂₁ =40250; f _T >6.5 ГГц	SOT346,SC59	
(M	2SC4593	REN	npn	V _{GB0} =15 B; I _C =50 mA; P _D =100 mBr; h ₂₁ =40250; f _T >6.5 FF _U	SOT323,SC70	
M	BZX99-C2V7	PHIL	dz	V ₂ (I _{ZT} =50 мкА)=2.572.84 В;Р _D <300 мВт	SOT23,SOD23	A·n.c.·K
M	RN1111	TOSH	Dnpn	V_{CE0} = 50 B; I_C = 150 mA; P_0 = 100 mBr; f_T > 250 MFu; R_1 = 10 kOm	SOT416,SC75A	B·E·C
M	RN1111F	TOSH	Dnpn	V_{CED} =50 B; I_C =150 mA; P_D =100 mBT; f_T >250 MF $_U$; R_1 =10 kOm	SOT490,SC89	B-E-C
(M	RN1111FT	TOSH	Dnpn	V_{CE0} = 50 B; I_C = 150 mA; P_D = 100 mBt; f_T > 250 MFu; R_T = 10 kOm	TESM	B·E·C
M	RN1311	TOSH	Dnpn	V_{CEO} =50 B; I_C =100 mA; P_O =100 mBt; f_T =250 MFu; R_T =10 kOm	SOT323,SC70	B·E·C
M	RN1411	TOSH	Dnpn	V_{CEO} =50 B; I_C =100 mA; P_D =200 mBT; f_T =200 MFu; R_1 =10 kOm	SOT346,SC59	B·E·C
Ms	BCR583	INF	Dpnp	V_{CB0} =50 B; I_C =500 mA; P_D =330 mBT; h_{21} >70; f_T >150 M Γ_{II}	SOT23,SOD23	B·E·C
(N	BZX99-C3V0	PHIL	dz	V _Z (I _{ZT} =50 mKA)=2.853.15B;P _D <300 mBt	SOT23,SOD23	A·n.c.·K
(N	RN1112	TOSH	Dnpn	V _{CED} =50 B; I _C =150 mA; P _D =100 mBt; f _T >250 MFu; P _t =22 kOm	SOT416,SC75A	B-E-C
(N	RN1112F	TOSH	Dnpn	V _{CEO} =50 B; I _C =150 mA; P _O =100 mBT; f _T >250 MFu; R _I =22 kOm	SOT490,SC89	B-E-C
(N	RN1112FT	TOSH	Dnpn	V _{CED} =50 B; I _C =150 мА; P _D =100 мВт; f _T >250 МГц; R ₁ =22 кОм	TESM	B·E·C
(N	RN1312	TOSH	Dnpn	V _{CED} =50 B; I _C =100 мА; P _D =100 мВт; f _T =250 МГц; R _T =22 кОм	SOT323,SC70	B-E-C
(N	RN1412	TOSH	Dnpn	V _{CF0} =50 B; I _C =100 mA; P _D =200 mB _T ; f _T =200 MFu; R ₁ =22 kOm	SOT346.SC59	100000000000000000000000000000000000000
(P	BZX99-C3V3	PHIL	dz	V ₂ (I _{2T} =50 mKA)=3.143.47 B; P _D <300 mBT	SOT23,SOD23	
P	MMBD3000T1	MOT	di	V _B <30 B; I _F <200 mA; V _F (I _F =10 mA)<0.95B; C _D <2 πΦ; t _{BB} <3 HC	SOT346,SC59	
P	RN1113	TOSH	Dnpn	V _{GEO} =50 B; I _G =150 mA; P _D =100 mBr; f _T >250 MFu; B ₁ =47 κOm	SOT416,SC75A	200000000000000000000000000000000000000
(P	RN1113F	TOSH	Dnpn	V _{DED} = 50 B; I _D = 150 MA; P _D = 100 MBT; f _T > 250 MFu; B; = 47 kOM	SOT490,SC89	-0.000.00
(P	RN1113FT	TOSH	Dnpn	V _{CED} =50 B; I _C =150 MA; P _D =100 MB; f _T >250 MFu; R ₁ =47 KOM	TESM	B·E·C

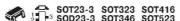




Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
XΡ	RN1313	TOSH	Dnpn	V _{CEO} =50 B; I _C =100 мA; P _D =100 мВт; f _T =250 МГц; R ₁ =47 кОм	SOT323,SC70	B·E·C
XΡ	RN1413	TOSH	Dnpn	V _{CEO} =50 B; I _C =100 мА; P _D =200 мВт; f _T =200 МГц; R ₁ =47 кОм	SOT346,SC59	B·E·C
XQ	2PD602AQ	PHIL	npn	V _{CB0} =60 B; I _C =500 мА; P _D =250 мВт; h ₂₁ =85170; f _T >140 МГц	SOT346,SC59	B·E·C
XQ	MMBD3005T1	MOT	di×2	V _B <30B; I _F <200 mA; V _F (I _F =10 mA)<0.95 B	S0T346,SC59	K1 · K2 · A1, A2
XQ	RN1114	TOSH	Dnpn	V _{CEO} =50B;I _C =100 mA;P _D =100 mBT;f _T >250 MFu;R ₁ /R ₂ =1/10 kOm	SOT416,SC75A	B·E·C
XQ	RN1114F	TOSH	Dnpn	V _{CEO} =50B;I _C =100mA;P _D =100mBT;f _T >250MFu;R ₁ /R ₂ =1/10kOm	S0T490,SC89	B·E·C
XQ	RN1114FT	TOSH	Dnpn	V _{CEO} =50B;I _C =100 MA;P _D =100 MBT;f _T >250 MFu;R ₁ /R ₂ =1/10 kOM	TESM	B·E·C
XQ	RN1314	TOSH	Dnpn	V _{CEO} =50 B; I _C =100 mA; P _D =100 mBT; f _T =250 MFu; R ₁ /R ₂ =1 kOm/10 kOm	S0T323,SC70	B·E·C
XQ	RN1414	TOSH	Dnpn	V _{CEO} =50 B; I _C =100 mA; P _D =200 mBT; I _T =200 MFu; R ₁ /R ₂ =1/10 kOm	S0T346,SC59	B·E·C
XO	RN2114FT	TOSH	Dono	V _{CBO} =50 B; I _C =100 mA; P _D =100 mBr; f _T =200 MFu; R ₁ /R ₂ =1 kOm/10 kOm	TESM	B·E·C
XR	2PD602AR	PHIL	non	V _{CR0} =60 B; I _n =500 mA; P _D =250 mBT; h ₂₁ =120240; f _T >160 MFu	SOT346,SC59	B·E·C
XR	BZX99-C3V6	PHIL	dz	V _Z (I _{ZT} =50mKA)=3.423.78 B; P _D <300 mBt	SOT23.SOD23	1001775191
XS	2PD602AS	PHIL	non	V _{CB0} =60B; I _C =500 мА; P ₀ =250 мВт; h ₂₁ =170340; f ₁ >180 МГц	SOT346,SC59	
XS	BZX99-C3V9	PHIL	dz	V ₂ (I _{2T} =50mKA)=3.714.1 B; P _D <300 mBT	SOT23.SOD23	
XS	MMBD3010	MOT	di×2	V _B < 30 B; I _E < 200 mA; V _E (I _E = 10 mA) < 0.95 B; C _B < 2 nΦ; I _{BB} < 3 HC	SOT346,SC59	
XS	RN1115	TOSH	Dnpn	V _{CF0} *50B;I _C *150 MA;P _D *100 MBT;f _T >250 MFц;R ₁ /R ₂ *2.2/10 кОм	S0T416,SC75A	
XS	RN1115F	TOSH	Dnpn	V _{CF0} ² 50 B; I _C ² 150 MA; P _D ² 100 MBT; I _T > 250 MFL; R ₁ /R ₂ ² 2.2/10 KOM	SOT490,SC89	
XS	RN1115FT	TOSH	Dnpn	V _{CEO} *50B; I _C *150 MA; P _D *100 MBT; f _T >250 MFu; R ₁ /R ₂ *2.2/10 KOM	TESM	B·E·C
XS	RN1315	TOSH	Dnon	V _{CEO} : 50 B; I _C : 100 MA; P _D : 100 MBT; f _T : 250 MFu; R ₁ /R ₂ : 2.2 KOM/10 KOM	SOT323.SC70	
XS	RN1415	TOSH	Dnon	V _{CF0} *50B;I _C *100MA;P _D *100MBT;I _T *200MFu;R ₁ /R ₉ *2.2/10KOM	SOT346.SC59	T-1075-176
XS	RN2115FT	TOSH	Dono	V _{CBO} =50B; I _C =100 MA; P _O =200 MB; I _T =200 MFц; R ₁ /R ₂ =2.2 kOM/10 kOM	TESM	B·E·C
XT	2SC4674	REN		V _{CB0} =12B; I ₀ =8mA; P ₀ =50mBT; h ₂₁ =50250; f _T >4 ITu	SOT323.SC70	
XT	BZX99-C4V3	PHIL	npn dz	V ₂ (I ₂₇ =50mKA)=4.094.52 B; P ₀ < 300 mBt	SOT23,SOD23	
XT		TOSH			S0T416,SC75A	
	RN1116		Dnpn	V _{CEO} *50 B;I _C *150 mA; P _D *100 mB;;f _T >250 MFu; R ₁ /R ₂ *4.7/10 κOm		1-50 150 15
XT	RN1116F	TOSH	Dnpn	V _{CEO} ⁻ 50B;I _C ⁻ 150 MA;P _D ⁻ 100 MBT;f _T >250 MΓu;R ₁ /R ₂ ⁻ 4.7/10 κOM	S0T490,SC89	
XT	RN1116FT	TOSH	Dnpn	V _{CEO} *50B;I _C *150 мA;P _D *100 мBT;f _T >250 MFu;R ₁ /R ₂ *4.7/10 κOm	TESM	B-E-C
XT	RN1316	TOSH	Dnpn	V _{CE0} *50B;I _C *100 мA;P _D *100 мBτ;f _T *250 MΓц;R ₁ /R ₂ *4.7 κOм/10 κOм	SOT323,SC70	
XT	RN1416	TOSH	Dnpn	$V_{CE0}^{-}50B;I_{C}^{-}100$ mA; $P_{0}^{-}200$ mB $\tau;f_{T}^{-}200$ MF $\tau;R_{1}/R_{2}^{-}4.7/10$ kOm	SOT346,SC59	
XT	RN2116FT	TOSH	Dpnp	V _{CB0} = 50 B; I _C = 100 mA; P _D = 100 mBT; f _T = 200 MFu; R ₁ /R ₂ = 4.7 kOm/10 kOm	TESM	B·E·C
XU	2SC4680	REN	non	V _{CB0} =12B; I _C =50 мA; P _D =150 мB⊤; h ₂₁ >100	SOT346,SC59	LOSS OF CURCO.
XU	BZX99-C7V5	PHIL	dz	V _Z (I _{ZT} =50 mKA)=7.137.88 B; P _D <300 mBτ	SOT23,SOD23	F1000000000000000000000000000000000000
XU	RN1117	TOSH	Dnpn	V _{CE0} =50B;I _C =150 мA;P _D =100 мBт;f _T >250 МГц;R ₁ /R ₂ =10/4.7 кОм	S0T416,SC75A	
XU	RN1117F	TOSH	Dnpn	V_{CE0} : 50 B; I_C : 150 mA; P_D : 100 mB;; f_T > 250 MFu; R_1/R_2 : 10/4.7 kOm	SOT490,SC89	
XU	RN1117FT	TOSH	Dnpn	V_{CE0} : 50 B; I_C : 150 mA; P_D : 100 mBT; f_T > 250 MFu; R_1/R_2 : 10/4.7 kOm	TESM	B-E-C
XU	RN1317	TOSH	Dnpn	V_{CE0} = 50 B; I_C = 100 mA; P_D = 100 mBT; f_T = 250 MFu; R_1/R_2 = 10 kOm/4.7 kOm	SOT323,SC70	
XU	RN1417	TOSH	Dnpn	V_{CE0} =50B; I_C =100 MA; P_0 =200 MBT; f_T =200 MFu; R_1/R_2 =10/4.7 KOM	S0T346,SC59	
XU	RN2117FT	TOSH	Dpnp	V _{CB0} =50 B; I _C =100 mA; P ₀ =100 mBτ; f _T =200 MΓц; R ₁ /R ₂ =10 κOm/4.7 κOm	TESM	B·E·C
XU-	2SC4680	REN	npn	V _{CB0} =12B; I _C =50 мA; P _D =150 мВт; h ₂₁ >100;	SOT23,SOD23	200010100
XUs	BCR562	INF	Dpnp	V_{CB0} =50 B; I_C =500 mA; P_D =330 mBr; h_{21} >60; f_T >150 M Γ_L	SOT23,SOD23	B·E·C
XV	BZX99-C8V2	PHIL	dz	V _Z (I _{ZT} =50 mKA)=7.798.61 B;P _D <300 mBt	SOT23,SOD23	A•n.c.•K
XVs	BCR521	INF	Dnpn	V_{CB0} =50B; I_C =500 mA; P_D =330 mBT; h_{21} >20; f_T >100M Γ_{IJ}	SOT23,SOD23	B•E•C
XW	BZX99-C9V1	PHIL	dz	V _Z (I _{ZT} = 50 mkA) = 8.659.56 B; P _D < 300 mBτ	SOT23,SOD23	A•n.c.•K
XW	RN1118	TOSH	Dnpn	V_{CE0} =50B; I_C =150 mA; P_D =100 mBT; f_T >250 MFu; R_1/R_2 =47/10 kOm	S0T416,SC75A	B·E·C
X₩	RN1118F	TOSH	Dnpn	V _{CE0} =50 B;I _C =150 mA;P _D =100 mBT;f _T >250 MFu;R ₁ /R ₂ =47/10 kOm	SOT490,SC89	B·E·C
X₩	RN1118FT	TOSH	Dnpn	V _{CE0} =50 B; I _C =150 мA; P _D =100 мВт; f _T >250 МГц; R ₁ /R ₂ =47/10 кОм	TESM	B·E·C
XW	RN1318	TOSH	Dnpn	V _{CEO} =50B;I _C =100 мA;P _D =100 мВт;f _T =250МГц;R ₁ /R ₂ =47 кОм/10 кОм	SOT323,SC70	B·E·C
X₩	RN1418	TOSH	Dnpn	V _{CE0} =50B;I _C =100 мA;P _D =200 мBт;f _T =200 МГц;R ₁ /R ₂ =47/10 κOм	SOT346,SC59	B·E·C
XW	RN2118FT	TOSH	Dpnp	V _{CBO} =50 B; I _C =100 mA; P _D =100 mBT; f _T =200 MFu; R ₁ /R ₂ =47 κOm/10 κOm	TESM	B-E-C
XWs	BCR505	INF	Dnpn	V _{CB0} =50B; I _C =500 мА; P _D =330 мВт; h ₂₁ >70; f _T >100 МГц	SOT23,SOD23	B·E·C
XX	BZX99-C10	PHIL	dz	V ₂ (I ₂₇ =50 mKA)=9.510.5 B; P ₀ < 300 mB _T	SOT23,SOD23	
XXs	BCR571	INF	Dono	V _{CR0} =50B; I _C =500 MA; P _D =330 MBT; h ₂₁ > 20; f _T > 150 MFц	SOT23,SOD23	100000000000000000000000000000000000000
XY	BZX99-C11	PHIL	dz	V _Z (I _{ZI} = 50 mKA) = 10.4511.55B;P _D < 300 mB	SOT23,SOD23	

SOT490 TESM VMT3 1 3 SOT523 SOT323 SOT23-3 1 3 SOT523 SOT323 SOT3

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
۷Z	BZX99-C12	PHIL	dz	V ₂ (I _{ZT} =50 MKA)=11.412.6B;P _D <300 MBt	SOT23,SOD23	A·n.c.·K
Z-	2SC5628	REN	npn	V _{CB0} =15 B; I _C =50 мА; Р ₀ =80 мВт; h ₂₁ =80160; f _T >6 ГГц	SC81,MFPAK	B-E-C
Œ-	2SC5629	REN	npn	V _{CB0} =15 B; I _C =50 mA; P ₀ =80 mBr; h ₂₁ =80160; f _T >2 ΓΓц	SOT416,SC75A	B-E-C
/1	BZX84C11	ALLEG	dz	V ₂ (I _{ZT} =5mA)=10.411.6B;I ₁ (V _B =8.0B)<0.1 mkA;Z _{ZT} (I _{ZT} =5 mA)<20 0m	SOT23,SOD23	A·n.c.·K
/1	BZX84C11	CSI	dz	$V_2(I_{2T}^{-5}MA)^{-1}0.411.6B; I_2(V_B^{-8}.0B) \le 0.1 \text{ mcA}; Z_{2T}(I_{2T}^{-5}MA) \le 20 \text{ Om}; I_{2M} \le 23 \text{ mA}$	SOT23,SOD23	A·n.c.·K
/1	BZX84C11	VISH	dz	$V_2(I_{ZT}=5 \text{ mA})=10.411.6 \text{ B}; Z_{ZT}(I_{ZT}=5 \text{ mA}) \le 200 \text{ m}$	SOT23,SOD23	
/1	BZX84C11LT1	MOT	dz	V _Z (I _{ZT} =5mA)=10.411.6B; Z _{ZT} (I _{ZT} =5mA)<200m	SOT23,SOD23	A·n.c.·K
/10	BZX84C27	ALLEG	dz	$V_2(I_{ZT}=2 \text{ mA})=25.128.9 \text{ B}; I_2(V_R=21.0 \text{ B}) < 0.05 \text{ m/A}; Z_{ZT}(I_{ZT}=2 \text{ mA}) < 80 \text{ Om}$	SOT23,SOD23	
/10	BZX84C27	CSI	dz	$\begin{array}{l} V_Z(I_{ZT}^{-2}\text{mA})^{+}25.128.9B; I_L(V_{B}^{-1}8.9B) \leq 0.05\text{mxA}; Z_{ZT}(I_{ZT}^{-2}\text{mA}) \leq 80\text{Om}; \\ I_{ZM}^{-2} \leq 9\text{mA} \end{array}$	SOT23,SOD23	A·n.c.·K
/10	BZX84C27	PHIL	dz	$\begin{array}{l} V_Z(I_{ZT}\!=\!2\text{MA})\!=\!25.128.9B;I_L(V_B\!=\!18.9B)\!\leq\!50\text{HA};Z_{ZT}(I_{ZT}\!=\!2.0\text{MA})\!\leq\!80\text{OM};\\ I_{ZM}\!=\!200\text{MA} \end{array}$	SOT23,SOD23	A•n.c.•K
Y10	BZX84C27	VISH	dz	V _Z (I _{ZT} =2 mA)=25.128.9 B; Z _{ZT} (I _{ZT} =2 mA) ≤ 80 Om	SOT23,SOD23	A·n.c.·K
Y11	BZX84C30	ALLEG	dz	$V_Z(I_{ZT} = 2 \text{ mA}) = 28.032.0 \text{ B}; I_L(V_R = 18.9 \text{ B}) < 0.05 \text{ m/A}; Z_{ZT}(I_{ZT} = 2 \text{ mA}) < 80 \text{ Om}$	SOT23,SOD23	A·n.c.·K
Y11	BZX84C30	CSI	dz	$\frac{V_Z(I_{ZT}\!=\!2\text{MA})\!=\!28.032.0B;I_L(V_B\!=\!21.0B)\!\leq\!0.05\text{mKA};Z_{ZT}\!(I_{ZT}\!=\!2\text{MA})\!\leq\!80\text{Om};}{I_{ZM}\!\leq\!8\text{mA}}$	SOT23,SOD23	A·n.c.·K
Y11	BZX84C30	PHIL	dz	$V_Z(I_{ZT}$ = 2 MA) = 28.032.0 B; $I_L(V_B$ = 21.0 B) < 50 HA; $Z_{ZT}(I_{ZT}$ = 2.0 MA) < 80 OM; I_{ZM} = 200 MA	SOT23,SOD23	A•n.c.•K
Y11	BZX84C30	VISH	dz	$V_2(I_{ZT}=2mA)=28.032.0B; Z_{ZT}(I_{ZT}=2mA) \le 800m$	SOT23,SOD23	
Y11	BZX84C30LT1	MOT	dz	$V_2(I_{ZT}=2mA)=28.032.0B; Z_{ZT}(I_{ZT}=2mA) \le 800m$	SOT23,SOD23	A·n.c.·K
/12	BZX84C33	ALLEG	dz	$V_2(I_{ZT}=2 \text{ mA})=31.035.0 \text{ B}; I_L(V_R=23.1 \text{ B}) < 0.05 \text{ m/A}; Z_{ZT}(I_{ZT}=2 \text{ mA}) < 80 \text{ Om}$	SOT23,SOD23	A·n.c.·K
Y12	BZX84C33	CSI	dz	$\frac{V_Z(I_{ZT}\text{-}2\text{MA})\text{-}31.035.0\text{B;}I_L(V_R\text{-}23.1\text{B})\text{<}0.05\text{mkA;}Z_{ZT}(I_{ZT}\text{-}2\text{mA})\text{<}80\text{Om;}}{I_{ZM}\text{<}7\text{mA}}$	SOT23,SOD23	A•n.c.•K
Y12	BZX84C33	PHIL	dz	$V_Z(I_{ZT} = 2 \text{ MA}) = 31.035.0 \text{ B; } I_L(V_B = 23.1 \text{ B}) \le 50 \text{ MA; } Z_{ZT}(I_{ZT} = 2.0 \text{ MA}) \le 80 \text{ Om; } I_{ZM} = 200 \text{ MA}$	SOT23,SOD23	A·n.c.·K
/12	BZX84C33	VISH	dz	V _Z (I _{ZT} =2mA)=31.035.0B;Z _{ZT} (I _{ZT} =2mA)≤800m	SOT23,SOD23	A·n.c.·K
/12	BZX84C33LT1	MOT	dz	V _Z (I _{ZT} =2mA)=31.035.0B;Z _{ZT} (I _{ZT} =2mA)≤800m	SOT23,SOD23	A·n.c.·K
Y13	BZX84C36	PHIL	dz	$V_z(I_{ZT} = 2 \text{ MA}) = 34.038.0 \text{ B}; I_z(V_B = 25.2 \text{ B}) \le 50 \text{ MA}; Z_{ZT}(I_{ZT} = 2.0 \text{ MA}) \le 90 \text{ OM}; I_{ZM} = 200 \text{ MA}$	SOT23,SOD23	A·n.c.·K
Y13	BZX84C36	VISH	dz	V _Z (I _{ZT} =2mA)=33.038.0B; Z _{ZT} (I _{ZT} =2mA)<900m	SOT23,SOD23	A·n.c.·K
Y13	BZX84C36LT1	MOT	dz	$V_2(I_{ZT}=2 \text{ mA})=33.038.0 \text{ B}; Z_{ZT}(I_{ZT}=2 \text{ mA}) \le 90 \text{ Om}$	SOT23,SOD23	A·n.c.·K
Y14	BZX84C39	PHIL	dz	$V_Z(I_{ZT}$ = 2 MA) = 37.041.0 B; $I_L(V_B$ = 27.3 B) < 50 HA; $Z_{ZT}(I_{ZT}$ = 2.0 MA) < 75 OM; I_{ZM} = 250 MA	SOT23,SOD23	A•n.c.•K
Y14	BZX84C39	VISH	dz	V _Z (I _{ZT} =2 mA)=36.041.0 B; Z _{ZT} (I _{ZT} =2 mA)≤130 Om	SOT23,SOD23	A·n.c.·K
Y14	BZX84C39LT1	MOT	dz	V _Z (I _{ZT} =2mA)=36.041.0B; Z _{ZT} (I _{ZT} =2mA)<130 Om	SOT23,SOD23	A•n.c.•K
Y15	BZX84C43	PHIL	dz	$\frac{V_Z(I_{ZT}\!=\!2\text{MA})\!=\!40.046.0B;I_{\{V_B\!=\!30.1B\}}\!<\!50\text{HA};Z_{ZT}(I_{ZT}\!=\!2.0\text{MA})\!<\!150\text{Om};}{I_{ZM}\!=\!200\text{MA}}$	SOT23,SOD23	A•n.c.•K
/15	BZX84C43	VISH	dz	$V_z(I_{ZT}=2 \text{ mA})=40.046.0 \text{ B}; Z_{ZT}(I_{ZT}=2 \text{ mA}) \le 150 \text{ Om}$	SOT23,SOD23	A·n.c.·K
/15	BZX84C43LT1	MOT	dz	V _Z (I _{ZT} =2mA)=40.046.0B; Z _{ZT} (I _{ZT} =2mA) < 150 Om	SOT23,SOD23	100000000000000000000000000000000000000
/16	BZX84C47	PHIL	dz	$ \begin{array}{l} V_Z(I_{ZT}\text{-}2\text{-MA})\text{-}44.050.0B;I_L(V_B\text{-}32.9B)\text{-}50\text{HA};Z_{ZT}(I_{ZT}\text{-}2.0\text{-MA})\text{-}170\text{Om};\\ I_{ZM}\text{-}200\text{MA} \end{array} $	SOT23,SOD23	10.10011.101
/16	BZX84C47	VISH	dz	$V_2(I_{ZT}=2mA)=44.050.0B; Z_{ZT}(I_{ZT}=2mA)<1700m$	SOT23,SOD23	
/16	BZX84C47LT1	MOT	dz	$V_2(I_{ZT}=2mA)=44.050.0B; Z_{ZT}(I_{ZT}=2mA)<1700m$	SOT23,SOD23	
17	BZX84C51	PHIL	dz	$V_Z(I_{ZT}^-2\text{mA})^+48.054.0\text{B;}I_L(V_R^-35.7\text{B})\!<\!50\text{HA;}Z_{ZT}(I_{ZT}^-2.0\text{mA})\!<\!180\text{Om;}I_{ZM}^-200\text{mA}$	SOT23,SOD23	
/17	BZX84C51	VISH	dz	$V_2(I_{ZT}=2mA)=48.054.0B; Z_{ZT}(I_{ZT}=2mA)<1800m$	SOT23,SOD23	
/17	BZX84C51LT1	MOT	dz	$V_2(I_{ZT}=2 \text{ mA})=48.054.0 \text{ B; } Z_{ZT}(I_{ZT}=2 \text{ mA}) \le 180 \text{ Om}$	SOT23,SOD23	
/18	BZX84C56	PHIL	dz	$V_Z(I_{ZT}^-2mA)^+52.060.0B;I_L(V_{B}^-39.2B)\!<\!50HA;Z_{ZT}(I_{ZT}^-2.0mA)\!<\!200Om;I_{ZM}^-200mA$	SOT23,SOD23	
/18	BZX84C56LT1	MOT	dz	$\frac{V_Z(I_{ZT}^-2\text{mA})^+52.060.0\text{B;}I_L(V_R^+39.2\text{B}) \leq 50\text{hA;}Z_{ZT}(I_{ZT}^+2.0\text{mA}) \leq 200\text{Om;}I_{ZM}^-200\text{mA}}$	SOT23,SOD23	- AND ALTONOUS BOX
/19	BZX84C62	PHIL	dz	$\frac{V_Z(I_{ZT}\!\!-\!2\text{MA})\!\!+\!58.066.0B;I_L\!(V_B\!\!-\!43.4B)\!\!<\!50HA;Z_{ZT}\!(I_{ZT}\!\!-\!2.0\text{MA})\!\!<\!215\text{OM};I_{ZM}\!\!-\!200\text{MA}}$	SOT23,SOD23	A•n.c.•K
/19	BZX84C62LT1	MOT	dz	$V_2(I_{ZT}=2MA)=58.066.0B;I_2(V_B=43.4B)\le 50MA;Z_{ZT}(I_{ZT}=2.0MA)\le 215O_{M};I_{ZM}=200MA$	SOT23,SOD23	A·n.c.·K





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
Y1p	BZX84C11	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ in A}) = 10.411.6B; I_L(V_R = 8.0B) < 100 \text{ in A}; Z_{ZT}(I_{ZT} = 5.0 \text{ in A}) < 20 \text{ On}; I_{ZM} = 200 \text{ in A}$	S0T23,S0D23	A•n.c.•K
Y1t	BZX84C11	PHIL	dz	$V_{X} _{Z_{I}} = 5 \text{ in A} = 10.411.6B; I_{L}\{V_{R} = 8.0B\} \le 100 \text{ HA}, Z_{Z}\{I_{ZT} = 5.0 \text{ in A}\} \le 200 \text{ nn}; I_{ZM} = 200 \text{ in A}$	SOT23,SOD23	A•n.c.•K
Y2	BZX84C12	ALLEG	dz	$V_Z(I_{ZT}=5 \text{ mA})=11.412.7 \text{ B}; I_L(V_R=8.0 \text{ B}) < 0.1 \text{ m/s}; Z_{ZT}(I_{ZT}=5 \text{ mA}) < 25 \text{ DM}$	SOT23,SOD23	A+n.c.+K
Y2	BZX84C12	CSI	dz	$V_Z(I_{ZT}=5\text{IMA})=11.412.7\text{B;}I_L(V_R=8.0\text{B}) \le 0.1\text{mkA;}Z_{ZT}(I_{ZT}=5\text{MA}) \le 25\text{Om;}I_{ZM} \le 21\text{IMA}$	SOT23,SOD23	A•n.c.•K
Y2	BZX84C12	VISH	dz	V _Z (I _{ZT} =5 mA)=11.412.7B;Z _{ZT} (I _{ZT} =5 mA)<250m	SOT23,SOD23	A+n.c.+K
Y2	BZX84C12LT1	MOT	dz	V _Z (I _{ZT} =5 mA)=11.412.7B;Z _{ZT} (I _{ZT} =5 mA)<250m	SOT23,SOD23	A•n.c.•K
Y20	BZX84C68	PHIL	dz	$ V_Z(I_{ZT}\!=\!2\text{MA})\!=\!64.6072.0\text{B}; I_L(V_B\!=\!47.6\text{B})\!<\!50\text{HA}; Z_{ZT}(I_{ZT}\!=\!2.0\text{MA})\!<\!240\text{Om}; I_{ZM}\!=\!200\text{MA}$	SOT23,SOD23	A•n.c.•K
Y21	BZX84C75	PHIL	dz	$\frac{V_Z(I_{ZT}\!-\!2\text{MA})\!=\!70.079.0B;I_L\!\{V_B\!-\!52.5B\}\!<\!50\text{HA};Z_{ZT}\!\{I_{ZT}\!=\!2.0\text{MA}\}\!<\!255\text{Om};}{I_{ZM}\!=\!200\text{MA}}$	SOT23,SOD23	122.03173.2,1326
Y2p	BZX84C12	PHIL	dz	$\frac{V_Z(I_{ZT}\!-\!5\text{mA})\!+\!11.412.7B;I_L(V_B\!-\!8.0B)\!<\!100\text{mA};Z_{ZT}(I_{ZT}\!-\!5.0\text{mA})\!<\!25\text{Om};}{I_{ZM}\!-\!200\text{mA}}$	SOT23,SOD23	X2000000000000000000000000000000000000
Y2t	BZX84C12	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ MA}) = 11.412.7 \text{ B; } I_L(V_B = 8.0 \text{ B}) \le 100 \text{ HA; } Z_{ZT}(I_{ZT} = 5.0 \text{ MA}) \le 250 \text{ m; } I_{ZM} = 200 \text{ MA}$	SOT23,SOD23	A•n.c.•K
Y3	BZX84C13	ALLEG	dz	$V_Z(I_{ZT}=5\text{mA})=12.414.1\text{B};I_L(V_R=8.0\text{B})<0.1\text{mkA};Z_{ZT}(I_{ZT}=5\text{mA})<30\text{Om}$	SOT23,SOD23	
Y3	BZX84C13	CSI	dz	$\frac{V_Z(I_{ZT}\!:\!5\text{Im}A)\!:\!12.414.1B;I_L\!(V_B\!:\!8.0B)\!<\!0.1\text{mkA};Z_{ZT}\!(I_{ZT}\!:\!5\text{Im}A)\!<\!30\text{Om};}{I_{ZM}\!<\!19\text{Im}A}$	SOT23,SOD23	
Y3	BZX84C13	VISH	dz	V _Z (I _{ZT} =5 MA)=12.414.1B;Z _{ZT} (I _{ZT} =5 MA)<30 OM	SOT23,SOD23	
Y3	BZX84C13LT1	MOT	dz	V _Z (I _{ZT} =5 mA)=12.414.1B;Z _{ZT} (I _{ZT} =5 mA)<30 Om	SOT23,SOD23	
Y36	BZX84-C13V6	PHIL	dz	V _Z (I _{ZT} =5 mA)=12.414.1B;Z _{ZT} (I _{ZT} =5 mA)<30 Om	SOT23,SOD23	200.00000000000000000000000000000000000
Y3p	BZX84C13	PHIL	dz	V _Z (I _{ZT} =5 MA)=12.414.1B; I _L (V _R =8.0B)<100 HA; Z _{ZT} (I _{ZT} =5.0 MA)<30 ON; I _{ZM} =200 MA	SOT23,SOD23	10.0000-10.000
Y3t	BZX84C13	PHIL	dz	V _Z (I _{ZT} = 5 mA) = 12.414.1 B; I _L (V _R = 8.0 B) < 100 hA; Z _{ZT} (I _{ZT} = 5.0 mA) < 30 On; I _{ZM} = 200 mA	SOT23,SOD23	
Y4	BZX84C15	ALLEG	dz	$V_Z(I_{ZT}=5 \text{ mA})=13.815.6 \text{ B}; I_L(V_R=10.5 \text{ B})<0.05 \text{ m/A}; Z_{ZT}(I_{ZT}=5 \text{ mA})<30 \text{ Om}$	SOT23,SOD23	100/2007/00/2007
Y4	BZX84C15	CSI	dz	$\begin{array}{l} V_Z(I_{ZT} \!$	SOT23,SOD23	
Y4	BZX84C15	VISH	dz	V _Z (I _{ZT} =5 mA)=13.815.6B;Z _{ZT} (I _{ZT} =5 mA)<30 Om	SOT23,SOD23	
Y4	BZX84C15LT1	MOT	dz	V _Z (I _{ZT} =5 MA)=13.815.6B;Z _{ZT} (I _{ZT} =5 MA)<30 OM	SOT23,SOD23	
Y4p	BZX84C15	PHIL	dz	$ \begin{array}{l} V_{Z}(I_{ZT}^{-}5MA) = 13.815.6B; I_{1}\{V_{p}^{-}10.5B\} < 0.05 \text{mrA}; \\ Z_{ZT}(I_{ZT}^{-}5.0 \text{mA}) < 300 \text{mr}, I_{ZM}^{-}200 \text{mA} \end{array} $	SOT23,SOD23	
Y4t	BZX84C15	PHIL	dz	$V_Z(I_{ZT}^-5 \text{ mA}) = 13.815.6B; I_L(V_B^-10.5B) < 0.05 \text{ mrA}; $ $Z_Z(I_{ZT}^-5.0 \text{ mA}) < 30 \text{ Om}; I_{ZM}^-200 \text{ mA}$	SOT23,SOD23	
Y5	BZX84C16	ALLEG	dz	$V_Z(I_{ZT}=5 \text{ mA})=15.317.1 \text{ B}; I_L(V_R=11.2 \text{ B})<0.05 \text{ mkA}; Z_{ZT}(I_{ZT}=5 \text{ mA})<40 \text{ Om}$	SOT23,SOD23	2010/03/2010/03/20
Y5	BZX84C16	CSI	dz	$\begin{array}{l} V_Z(I_{ZT} \!$	SOT23,SOD23	100000000000000000000000000000000000000
Y5	BZX84C16	VISH	dz	V _Z (I _{ZT} =5mA)=15.317.1B;Z _{ZT} (I _{ZT} =5mA)<400m	SOT23,SOD23	100000000000000000000000000000000000000
Y50	BZX84A2V4	PHIL	dz	$\frac{V_Z(I_{ZT}\!=\!5\text{MA})\!=\!2.372.43B;I_L\!\{V_R\!=\!1.0B\}\!\leq\!50\text{mKA};Z_{ZT}\!\{I_{ZT}\!=\!5.0\text{MA}\}\!\leq\!100\text{OM};}{I_{ZM}\!=\!200\text{MA}}$	SOT23,SOD23	100000000000000000000000000000000000000
Y51	BZX84A2V7	PHIL	dz	$\frac{V_Z(I_{ZT}\!\!-\!5\text{MA})\!\!-\!2.672.73B;I_L\!\{V_R\!\!-\!1.0B\}\!\!<\!20\text{mkA};Z_{ZT}\!(I_{ZT}\!\!-\!5.0\text{mA})\!\!<\!100\text{Om};}{I_{ZM}\!\!-\!200\text{mA}}$	SOT23,SOD23	
Y52	BZX84A3V0	PHIL	dz	$\frac{V_Z(I_{ZT}\!\!-\!5\text{MA})\!\!+\!2.973.03B;I_L\!(V_R\!\!-\!1.0B)\!\!<\!10\text{mKA};Z_{ZT}\!(I_{ZT}\!\!-\!5.0\text{MA})\!\!<\!950\text{m};}{I_{ZM}\!\!-\!200\text{MA}}$	SOT23,SOD23	
Y53	BZX84A3V3	PHIL	dz	$\begin{array}{l} V_Z(I_{ZT}\!\!=\!5\text{mA})\!\!=\!\!3.263.34B;I_L\!\{V_R\!\!=\!\!1.0B\}\!\!\leq\!\!5\text{mKA},Z_{ZT}(I_{ZT}\!\!=\!\!5.0\text{mA}\}\!\!\leq\!\!95\text{Om};\\ I_{ZM}\!\!=\!\!200\text{mA} \end{array}$	SOT23,SOD23	
Y54	BZX84A3V6	PHIL	dz	$\begin{array}{l} V_Z(I_{ZT}\!$	SOT23,SOD23	
Y55	BZX84A3V9	PHIL	dz	$\frac{V_Z(I_{ZT}\!:\!5\text{MA})\!:\!386394B;I_L\!\{V_{R}\!:\!1.0B\}\!<\!3\text{mKA};Z_{ZT}\!\{I_{ZT}\!:\!5.0\text{mA}\}\!<\!90\text{Dm};}{I_{ZM}\!:\!200\text{mA}}$	SOT23,SOD23	
Y56	BZX84A4V3	PHIL	dz	$\frac{V_Z(I_{ZT}\!\!=\!5\text{mA})\!\!=\!4.254.35B;I_L\!\{V_R\!\!=\!1.0B\}\!\!<\!3\text{mKA},Z_{ZT}(I_{ZT}\!\!=\!5.0\text{mA}\}\!\!<\!90\text{Om};}{I_{ZM}\!\!=\!200\text{mA}}$	SOT23,SOD23	
Y57	BZX84A4V7	PHIL	dz	$\begin{array}{l} V_Z(I_{ZT} \!$	SOT23,SOD23	
Y58	BZX84A5V1	PHIL	dz	V _Z (I _{ZT} = 5 MA) = 5.045.16 B; I _L (V _R = 2.0 B) < 2 m; A; Z _{ZT} (I _{ZT} = 5.0 mA) < 60 Om; I _{ZM} = 200 mA	SOT23,SOD23	Arn.c.+K

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
Y59	BZX84A5V6	PHIL	dz	$V_2(I_{ZT}=5\text{MA})=5.545.66\text{ B}$, $I_2(V_R=2.0\text{ B})<1$ m/cA; $Z_{ZT}(I_{ZT}=5.0\text{ mA})<40\text{ Om}$; $I_{ZM}=200\text{ mA}$	SOT23,SOD23	A·n.c.·K
Y5p	BZX84C16	PHIL	dz	Z ₂ (I _{Z1} =5mA)=15.317.1B; I _L (V _B =11.2B)<50 HA; Z _{Z1} (I _{Z1} =5.0 mA)<40 Om; I _{DM} =200 mA	SOT23,SOD23	A·n.c.·K
Y5t	BZX84C16	PHIL	dz	$V_2(I_{ZT}$ =5MA)=15.317.1B, $I_1(V_R$ =11.2B)<50HA; $I_{ZT}(I_{ZT}$ =5.0 MA)<40 On; I_{ZM} =200 MA	SOT23,SOD23	A•n.c.•K
Y6	BZX84C18	ALLEG	dz	V _Z (I _{ZT} =5mA)=16.819.1B; I _L (V _R =12.6B) < 0.05 mkA; Z _{ZT} (I _{ZT} =5 mA) < 45 Om	SOT23,SOD23	A·n.c.·K
Y6	BZX84C18	CSI	dz	$\frac{V_Z(I_{ZT}^{-5}\text{MA})^{-}16.819.1B;I_L(V_{R}^{-1}12.6B)\leq0.05\text{mkA};Z_{ZT}(I_{ZT}^{-5}\text{MA})\leq45\text{Om};I_{ZM}\leq14\text{MA}}$	SOT23,SOD23	A·n.c.·K
Y6	BZX84C18	VISH	dz	V _Z (I _{ZT} =5mA)=16.819.1B; Z _{ZT} (I _{ZT} =5mA)<450m	SOT23,SOD23	A·n.c.·K
Y6	BZX84C18LT1	MOT	dz	V ₂ (I _{ZT} =5mA)=16.819.1B;Z _{ZT} (I _{ZT} =5mA)<450m	SOT23,SOD23	100000000000000000000000000000000000000
Y60	BZX84A6V2	PHIL	dz	$\begin{array}{l} V_Z(I_{ZT}\text{-}5MA)\text{-}6.136.27B;I_L(V_B\text{-}4.0B)\text{-}3\text{mkA};Z_{ZT}(I_{ZT}\text{-}5.0\text{mA})\text{-}10\text{Om};\\ I_{ZM}\text{-}200\text{mA} \end{array}$	SOT23,SOD23	A·n.c.·K
Y61	BZX84A6V8	PHIL	dz	$V_Z(I_{ZT}=5 \text{ mA})=6.736.87 \text{ B}; I_L(V_R=4.0 \text{ B}) \le 2 \text{ mrA}; Z_{ZT}(I_{ZT}=5.0 \text{ mA}) \le 15 \text{ Om}; I_{ZM}=200 \text{ mA}$	SOT23,SOD23	A·n.c.·K
Y62	BZX84A7V5	PHIL	dz	$V_Z(I_{ZT}=5 \text{ MA})=7.427.58 \text{ B; }I_L(V_R=5.0 \text{ B}) \le 1 \text{ mrA; } Z_{ZT}(I_{ZT}=5.0 \text{ mA}) \le 15 \text{ Om; } I_{ZM}=200 \text{ mA}$	SOT23,SOD23	A·n.c.·K
Y63	BZX84A8V2	PHIL	dz	$V_Z(I_{ZT}=5\text{ mA})=8.118.29 \text{ B; } I_L(V_B=5.0 \text{ B}) \le 700 \text{ mA; } Z_{ZT}(I_{ZT}=5.0 \text{ mA}) \le 15 \text{ Ow; } I_{ZM}=200 \text{ mA}$	SOT23,SOD23	A·n.c.·K
Y64	BZX84A9V1	PHIL	dz	$V_2(I_{ZT} = 5MA) = 9.009.20 B; I_2(V_B = 6.0 B) < 500 HA; Z_{ZT}(I_{ZT} = 5.0 MA) < 15 Om; I_{ZM} = 200 MA$	SOT23,SOD23	A·n.c.·K
Y65	BZX84A10	PHIL	dz	$V_2(I_{ZT}=5 \text{ mA})=9.910.1; I_2(V_{R}=7.0 \text{ B}) \le 200 \text{ mA}; Z_{ZT}(I_{ZT}=5.0 \text{ mA}) \le 20 \text{ Om}; I_{ZM}=200 \text{ mA}$	SOT23,SOD23	A•n.c.•K
Y66	BZX84A11	PHIL	dz	$V_2(I_{ZT} = 5 \text{ MA}) = 10.811.11 \text{ B; } I_k(V_B = 8.0 \text{ B}) \le 100 \text{ HA; } Z_{ZT}(I_{ZT} = 5.0 \text{ MA}) \le 20 \text{ OM; } I_{ZM} = 200 \text{ MA}$	SOT23,SOD23	A•n.c.•K
Y67	BZX84A12	PHIL	dz	$V_2(I_{ZT}=5\text{MA})=11.8812.12\text{B}; I_2(V_{B}=8.0\text{B})<100\text{HA}; Z_{ZT}(I_{ZT}=5.0\text{MA})<25\text{Ow}; I_{ZM}=200\text{MA}$	SOT23,SOD23	A·n.c.·K
Y68	BZX84A13	PHIL	dz	$V_{Z} _{Z_{I}}=5$ mA)=12.8713.13 B; $I_{L}(V_{B}=8.0$ B) < 100 mA; $Z_{ZI}(I_{ZI}=5.0$ mA) < 30 Ow; $I_{ZM}=200$ mA	SOT23,SOD23	A•n.c.•K
Y69	BZX84A15	PHIL	dz	$V_{Z} _{Z_{T}}=5$ mA)=14.9152B; $I_{L}(V_{R}=10.5$ B)<0.05 mkA; $Z_{ZT}(I_{ZT}=5.0$ mA)<30 Om; $I_{ZM}=200$ mA	SOT23,SOD23	A•n.c.•K
Y6p	BZX84C18	PHIL	dz	$V_Z(I_{ZT}=5\text{MA})=16.819.1\text{ B; }I_L(V_B=12.6\text{ B}) \le 50\text{ HA; }Z_{ZT}(I_{ZT}=5.0\text{ MA}) \le 45\text{ On; }I_{ZM}=200\text{ MA}$	SOT23,SOD23	A·n.c.·K
Y6t	BZX84C18	PHIL	dz	V _Z (I _{ZT} =5mA)=16.819.1B; I _L (V _B =12.6B)<50 HA; Z _{ZT} (I _{ZT} =5.0 mA)<45 On; I _{ZM} =200 mA	SOT23,SOD23	A·n.c.·K
Y7	BZX84C20	ALLEG	dz	V _Z (I _{ZT} =5mA)=18.821.2B; I _L (V _B =14.0B)<0.05 mkA; Z _{ZT} (I _{ZT} =5mA)<55 Om	SOT23,SOD23	A·n.c.·K
Y7	BZX84C20	CSI	dz	$V_Z(I_{ZT} = 5 \text{ MA}) = 18.821.2 \text{ B; } I_Z(V_R = 14.0 \text{ B}) \le 0.05 \text{ MKA}; Z_{ZT}(I_{ZT} = 5 \text{ MA}) \le 55 \text{ Om}; I_{ZM} \le 12 \text{ MA}$	SOT23,SOD23	A·n.c.·K
Y7	BZX84C20	VISH	dz	V ₂ (I _{ZT} =5mA)=18.821.2B; Z _{ZT} (I _{ZT} =5mA)<55Om	SOT23,SOD23	A·n.c.·K
Y7	BZX84C20LT1	MOT	dz	V ₂ (I _{ZT} =5 mA)=18.821.2B; Z _{ZT} (I _{ZT} =5 mA)<55 Om	SOT23,SOD23	A·n.c.·K
Y70	BZX84A16	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ MA}) = 15.8416.16 \text{ B}; I_L(V_R = 11.2 \text{ B}) \le 50 \text{ MA}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) \le 40 \text{ Ow}; I_{ZM} = 200 \text{ mA}$	SOT23,SOD23	A•n.c.•K
Y71	BZX84A18	PHIL	dz	$V_2(I_{ZT}$ =5MA)=17.818.2B; $I_2(V_R$ =12.6B) <50HA; $Z_{ZT}(I_{ZT}$ =5.0 MA) <45 ON; I_{ZM} =200 MA	SOT23,SOD23	A·n.c.·K
Y72	BZX84A20	PHIL	dz	$V_Z(I_{Z1}$ =5MA)=19.820.2B; $I_L(V_R$ =14.0B) < 50HA; $Z_{Z1}(I_{Z1}$ =5.0 MA) < 55 On; I_{ZM} =200 MA	SOT23,SOD23	A•n.c.•K
Y73	BZX84A22	PHIL	dz	$V_{Z} _{Z_{I}}$ =5MA}=21.822.2B; $I_{L} _{V_{B}}$ =15.4B} < 50HA; $Z_{ZL} _{Z_{I}}$ =5.0 MA} < 55 On; I_{ZM} =200 MA	SOT23,SOD23	A·n.c.·K
Y74	BZX84A24	PHIL	dz	$V_Z(I_{ZT}=5\text{MA})=23.824.2B; I_L(V_B=16.8B) \le 50\text{HA}; Z_{ZT}(I_{ZT}=5.0\text{ MA}) \le 30\text{ Ont}; I_{ZM}=250\text{ MA}$	SOT23,SOD23	A·n.c.·K
Y75	BZX84A27	PHIL	dz	$V_Z(I_{ZT}=2mA)=26.727.3B$, $I_L(V_R=18.9B) \le 50 \text{ HA}$, $Z_{ZT}(I_{ZT}=2.0 \text{ mA}) \le 80 \text{ Om}$; $I_{ZM}=200 \text{ mA}$	SOT23,SOD23	A•n.c.•K
Y76	BZX84A30	PHIL	dz	$V_Z(I_{ZT} = 2 \text{ MA}) = 29.730.3 \text{ B; } I_L(V_R = 21.0 \text{ B}) \le 50 \text{ HA; } Z_{ZT}(I_{ZT} = 2.0 \text{ MA}) \le 80 \text{ Ont; } I_{ZM} = 200 \text{ MA}$	SOT23,SOD23	A•n.c.•K
Y77	BZX84A33	PHIL	dz	V _Z (I _{ZT} =2MA)=32.733.3B; I _L (V _R =23.1B)<50HA; Z _{ZT} (I _{ZT} =2.0 MA)<80 ON; I _{ZM} =200 MA	SOT23,SOD23	A•n.c.•K
Y78	BZX84A36	PHIL	dz	V _Z (I _{ZT} =2mA)=35.636.4B; I _L (V _R =25.2B)<50 HA; I _{ZT} (I _{ZT} =2.0 mA)<90 Om; I _{ZM} =200 mA	SOT23,SOD23	A·n.c.·K





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
Y79	BZX84A39	PHIL	dz	$V_Z(I_{ZT}=2\text{MA})=38.639.4\text{B};\ I_L(V_R=27.3\text{B})<50\text{HA};\ Z_{ZT}(I_{ZT}=2.0\text{MA})<75\text{Om};\ I_{ZM}=250\text{MA}$	SOT23,SOD23	A•n.c.•K
17p	BZX84C20	PHIL	dz	$\frac{V_Z(I_{ZT}=5\text{mA})}{I_{ZM}}=200\text{mA}}=18.821.2\text{B}; I_L(V_R=14.0\text{B}) \le 50\text{mA}; Z_{ZT}(I_{ZT}=5.0\text{mA}) \le 55\text{Om}; I_{ZM}=200\text{mA}$	SOT23,SOD23	A•n.c.•K
r7t	BZX84C20	PHIL	dz	$V_Z(I_{ZT}$ = 5 mA)= 18.821.2B; $I_L(V_R$ =14.0B} < 50 mA; $Z_{ZT}(I_{ZT}$ = 5.0 mA} < 55 0m; I_{ZM} =200 mA	SOT23,SOD23	A•n.c.•K
Y8	BZX84C22	ALLEG	dz	$V_Z(I_{ZT}=5 \text{ mA})=20.823.3 \text{ B}; I_L(V_R=15.4 \text{ B})<0.05 \text{ m/A}; Z_{ZT}(I_{ZT}=5 \text{ mA})<55 \text{ Om}$	SOT23,SOD23	A+n.c.+K
Y8	BZX84C22	CSI	dz	$V_Z(I_{ZT}\!\!=\!5\text{MA})\!\!=\!\!20.823.3B;I_L(V_R\!\!=\!\!15.4B\}\!<\!0.05\text{mrA};Z_{ZT}(I_{ZT}\!\!=\!\!5\text{MA})\!<\!\!55\text{Om};I_{ZM}\!<\!11\text{mA}$	SOT23,SOD23	A•n.c.•K
Y8	BZX84C22	VISH	dz	V _Z (I _{ZT} =5 mA)=20.823.3 B; Z _{ZT} (I _{ZT} =5 mA) < 55 Om	SOT23,SOD23	A·n.c.•K
Y8	BZX84C22LT1	MOT	dz	V _Z (I _{ZT} =5 mA)=20.823.3B;Z _{ZT} (I _{ZT} =5 mA)<55 Om	SOT23,SOD23	100010000000000000000000000000000000000
Y80	BZX84A43	PHIL	dz	$V_Z\{I_{ZT}\!=\!2\text{MA}\}\!=\!42.643.4B;I_L\{V_R\!=\!30.1B\}\!<\!50\text{HA};Z_{ZT}\{I_{ZT}\!=\!2.0\text{MA}\}\!<\!150\text{Om};I_{ZM}\!=\!200\text{MA}$	SOT23,SOD23	A•n.c.•K
Y81	BZX84A47	PHIL	dz	$V_Z(I_{ZT}=2\text{mA})=46.5\dots47.5\text{B}; I_L(V_R=32.9\text{B}) \le 50\text{mA}; Z_{ZT}(I_{ZT}=2.0\text{mA}) \le 170\text{Om}; I_{ZM}=200\text{mA}$	SOT23,SOD23	1000-0000 A 1000-00
Y82	BZX84A51	PHIL	dz	$V_Z(I_{ZT}=2\text{MA})=50.551.5B;I_L(V_B=35.7B)<50\text{HA};Z_{ZT}(I_{ZT}=2.0\text{MA})<180\text{Om};I_{ZM}=200\text{MA}$	SOT23,SOD23	A•n.c.•K
Y83	BZX84A56	PHIL	dz	$V_Z\{I_{ZT}=2\text{MA}\}=55.456.6\text{B};I_L\{V_R=39.2\text{B}\}\le 50\text{HA};Z_{ZT}\{I_{ZT}=2.0\text{MA}\}\le 200\text{OM};I_{ZM}=200\text{MA}$	SOT23,SOD23	SANGE SEE
Y84	BZX84A62	PHIL	dz	$V_Z\{I_{ZT}=2\text{MA}\}=61.462.6B;I_L\{V_{\tilde{B}}=43.4B\}\le 50\text{HA};Z_{ZT}\{I_{ZT}=2.0\text{MA}\}\le 215\text{Om};I_{ZM}=200\text{MA}$	SOT23,SOD23	
Y85	BZX84A68	PHIL	dz	$V_Z(I_{ZT}=2\text{mA})=67.368.7B;I_L(V_R=47.6B)<50\text{HA};Z_{ZT}(I_{ZT}=2.0\text{mA})<240\text{Om};I_{ZM}=200\text{mA}$	SOT23,SOD23	
Y86	BZX84A75	PHIL	dz	$V_Z(I_{ZT}=2\text{MA})=74.375.7B;I_L(V_R=52.5B)<50\text{HA};Z_{ZT}(I_{ZT}=2.0\text{MA})<255\text{Om};I_{ZM}=200\text{MA}$	SOT23,SOD23	
Y8p	BZX84C22	PHIL	dz	$\frac{V_Z(I_{ZT}=5\text{MA})=20.823.3B;I_L(V_{B^2}=15.4B)<50\text{HA};Z_{ZT}(I_{ZT}=5.0\text{mA})<55\text{O}\text{m};}{I_{ZM}=200\text{mA}}$	SOT23,SOD23	
Y8t	BZX84C22	PHIL	dz	$V_Z(I_{ZT}$ = 5 mA)= 20.823.3 B; $I_L(V_R$ = 15.4 B} < 50 hA; $Z_{ZT}(I_{ZT}$ = 5.0 mA) < 55 Om; I_{ZM} = 200 mA	SOT23,SOD23	A•n.c.•K
Y9	BZX84C24	ALLEG	dz	$V_Z(I_{ZT}=5 \text{ mA})=22.825.6 \text{ B}; I_L(V_R=16.8 \text{ B})<0.05 \text{ m/A}; Z_{ZT}(I_{ZT}=5 \text{ mA})<70 \text{ Om}$	SOT23,SOD23	1201-0100-0-010
Y9	BZX84C24	CSI	dz	$V_Z(I_{ZT}\!=\!5\text{MA})\!=\!22.825.6B;I_L(V_R\!=\!16.8B)\!<\!0.05\text{mrA};Z_{ZT}(I_{ZT}\!=\!5\text{mA})\!<\!70\text{Om};\\I_{ZM}\!<\!10\text{mA}$	SOT23,SOD23	A•n.c.•K
Y9	BZX84C24	VISH	dz	V _Z (I _{ZT} =5 mA)=22.825.6B;Z _{ZT} (I _{ZT} =5 mA)<70 Om	SOT23,SOD23	
Y9	BZX84C24LT1	MOT	dz	V _Z (I _{ZT} =5 mA)=22.825.6B;Z _{ZT} (I _{ZT} =5 mA)<70 Om	SOT23,SOD23	A·n.c.•K
Y9p	BZX84C24	PHIL	dz	$V_Z(I_{ZT}$ = 5 mA)= 22.825.6B; $I_L(V_R$ =16.8B} < 50 hA; $Z_{ZT}(I_{ZT}$ = 5.0 mA) < 30 0 m; I_{ZM} = 250 mA	SOT23,SOD23	A•n.c.•K
Y9t	BZX84C24	PHIL	dz	$V_Z(I_{ZT}$ = 5 mA)= 22.825.6B; $I_L(V_B$ = 16.8B} < 50 HA; $Z_{ZT}(I_{ZT}$ = 5.0 mA) < 30 Om; I_{ZM} = 250 mA	SOT23,SOD23	A•n.c.•K
YΑ	RN2101	TOSH	Dpnp	V _{CB0} =50 B; I _C =100 мА; P _D =200 мВт; I _T =250 МГц; R ₁ /R ₂ =4.7 кОм/4.7 кОм	S0T416,SC75A	B·E·C
YΑ	RN2101F	TOSH	Dpnp	V_{CB0} = 50 B; I_C = 100 mA; P_0 = 100 mBt; f_T =250 MFu; R_1/R_2 =4.7 kOm/4.7 kOm	SOT490,SC89	B·E·C
YΑ	RN2101FT	TOSH	Dpnp	V_{CB0} =50B; I_C =100 mA; P_D =100 mBt; f_T =250 MFu; R_1/R_2 =4.7 kOm/4.7 kOm	TESM	B·E·C
YΑ	RN2301	TOSH	Dpnp	V_{CB0} = 50 B; I_C = 100 mA; P_0 = 100 mBt; f_T = 200 M Γ_H ; R_1/R_2 = 4.7 kOm/4.7 kOm	SOT323,SC70	B·E·C
YΑ	RN2401	TOSH	Dpnp	V _{CE0} =50B;I _C =100 мA;P ₀ =200 мBт;I _T =200 МГц;R ₁ /R ₂ =4.7/4.7 кОм	SOT346,SC59	
YA-	2SC4784	REN	npn	V _{CB0} = 15B; I _C = 20 мА; P _D = 100 мВт; h ₂₁ =50250; f _T >7 ГТц	S0T323,SC70	B·E·C
YA-	2SC5049	REN	npn	V_{CB0} = 15 B; I_C = 20 mA; P_D = 150 mBT; h_{21} =50250; f_T >7 ГГц	SOT23,SOD23	B·E·C
YA-	2SC5543	REN	npn	V _{CB0} =15B; I _C =20 мA; P _D =80 мВт; h ₂₁ =85170; f _T >5.5 ГГц	SC81,MFPAK	C·B·E
ΥB	RN2102	TOSH	Dpnp	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBt; f_T = 250 MFu; R_1/R_2 = 10/10 kOm	S0T416,SC75A	B-E-C
ΥB	RN2102F	TOSH	Dpnp	V_{CB0} = 50 B; I_C = 100 mA; P_D = 100 mBT; f_T =250 MFu; R_1/R_2 =10/10 kOm	SOT490,SC89	B·E·C
ΥB	RN2102FT	TOSH	Dpnp	V_{CB0} =50B; I_C =100 mA; P_0 =100 mBt; f_T =250 MFu; R_1/R_2 =10/10 kOm	TESM	B-E-C
ΥB	RN2302	TOSH	Dpnp	V _{CB0} =50B; I _C =100 мА; P _D =100 мВт; f _T =200 МГц; R ₁ /R ₂ =10 кОм/10 кОм	S0T323,SC70	B·E·C
ΥB	RN2402	TOSH	Dpnp	V _{CE0} =50 B; I _C =100 mA; P _D =200 mBT; f _T =200 MFu; R ₁ /R ₂ =10/10 kOm	S0T346,SC59	B·E·C
YBs	BSS84	INF	pMOS	V _{DS} =50 B;I _D =130 mA;P _D =360 mBT; g _E =50 mCm; R _{DS(m)} =10 0m	SOT23,SOD23	G·S·D
YC	RN2103	TOSH	Dpnip	V _{CB0} =50B; I _C =100 мА; P _D =200 мВт; f _T =250 МГц; R ₁ /R ₂ =22/22 кОм	S0T416,SC75A	B-E-C
YC	RN2103F	TOSH	Dono	V _{CB0} =50 B; I _C =100 mA; P _D =100 mBt; I _T =250 MFu; R ₁ /R ₂ =22/22 kOm	S0T490,SC89	
YC	RN2103FT	TOSH	Dono	V _{CRO} =50B; I _C =100 mA; P _D =100 mBt; f _T =250 MFu; R ₁ /R ₂ =22/22 kOm	TESM	B-E-C
YC	RN2303	TOSH	Donio	V _{CB0} =50B; I _C =100 mA; P _D =100 mBt; f _T =200 MFt; R ₁ /R ₂ =22 kOm/22 kOm	SOT323,SC70	

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
/C	RN2403	TOSH	Dono	V _{CEO} =50 B; I _C =100 mA; P _D =200 mBt; f _T =200 MFu; R ₁ /R ₂ =22/22 kOm	SOT346,SC59	B-E-C
/D	RN2104	TOSH	Dono	V _{CR0} =50 B; I _C =100 MA; P _D =200 MB; f _T =250 MFu; R ₃ -47/47 KOM	SOT416.SC75A	
/D	RN2104F	TOSH	Donp	V _{CB0} =50 B; I _C =100 мА; P _D =100 мВт; f _T =250 МГц; R ₁ /R ₂ =47/47 кОм	SOT490.SC89	
YD	RN2104FT	TOSH	Dono	V _{CP0} =50 B; I _C =100 mA; P _D =100 mBT; f _T =250 MFu; R ₁ /R ₂ =47/47 KOm	TESM	B·E·C
/D	RN2304	TOSH	Dono	V _{CR0} =50 B; I _C =100 мА; P _D =100 мВт; f _T =200 МГц; R ₁ /R ₂ =47 кОм/47 кОм	SOT323,SC70	
/D	RN2404	TOSH	Dono	V _{CB0} =50 B; I _C =100 мА; Р ₀ =200 мВт; f _T =200 МГц; R ₁ /R ₂ =47/47 кОм	SOT346.SC59	
Æ	RN2105	TOSH	Donp	V _{CB0} =50 B; I _C =100 мА; P _D =200 мВт; f _T =250 МГц; R ₁ /R ₂ =2.2/47 кОм	SOT416,SC75A	707 0
Æ	RN2105F	TOSH	Dono	V _{CR0} =50 B; I _C =100 mA; P _D =100 mBT; f _T =250 MFu; R ₁ /R ₂ =2.2/47 кОм	SOT490.SC89	
Æ	RN2105FT	TOSH	Dono	V _{CR0} =50 B; I _C =100 mA; P _D =100 mB _T ; F _T =250 MF _U ; R ₁ /R ₂ =2.2/47 κOm	TESM	B·E·C
Æ	RN2305	TOSH	Donp	V _{CB0} =50 B; I _C =100 MA; P _D =100 MBT; F _T =200 MFU; R ₁ /R ₂ =2.2 KOM/47 KOM	SOT323.SC70	
Æ	RN2405	TOSH	Donp	V _{CEO} =50 B; I _C =100 MA; P _D =200 MBT; I _T =200 MTu; R ₁ /R ₂ =2.2 KOM/47 KOM	SOT346,SC59	
/F	RN2106	TOSH	Dono	V _{CBD} =50 B; I _C =100 мA; P _D =200 мB; f _T =250 МГц; R ₁ /R ₂ =4.7/47 кОм	SOT416.SC75A	17503200000
/F	RN2106F	TOSH	Dono	V _{CB0} =50 B; I _C =100 MA; P _D =200 MB; F _T =250 MFц; R ₁ /R ₂ =4.7/47 κOM	SOT490.SC89	
/F	RN2106FT	TOSH	Dono	V _{CBO} =50 B; I _C =100 MA; P _D =100 MB; I _T =250 MΓц; R ₁ /R ₂ =4.7/47 κOM	TESM	B·E·C
/F	RN2306	TOSH	101		SOT323.SC70	200-21
/F		_	Dpnp	V _{GB0} =50 B; I _C =100 mA; P _D =100 mBr; f _T =200 MFu; R ₁ /R ₂ =4.7 κOm/47 κOm	SOT346,SC59	
_	RN2406	TOSH	Dpnp	V _{CEO} =50 B; I _C =100 mA; P _O =200 mBr; f _T =200 MFu; R ₁ /R ₂ =4.7/47 kOm		
/H	RN2107	TOSH	Dpnp	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBt; F _T =250 MFt; R ₁ /R ₂ =10/47 κOm	SOT416,SC75A	
/H	RN2107F	TOSH	Dpnp	V _{GB0} =50 B; I _C =100 мA; P _D =100 мВт; f _T =250 МГц; R ₁ /R ₂ =10/47 кОм	SOT490,SC89	70070070
/H	RN2107FT	TOSH	Dpnp	V _{CB0} =50 B; I _C =100 мA; P _D =100 мВт; f _T =250 МГц; R ₁ /R ₂ =10/47 кОм	TESM	B·E·C
/H	RN2307	TOSH	Dpnp	V _{CB0} =50 B; I _C =100 мA; P _D =100 мВт; f _T =200 МГц; R ₁ /R ₂ =10 кОм/47 кОм	SOT323,SC70	
/H	RN2407	TOSH	Dpnp	V_{CED} =50 B; I_C =100 mA; P_D =200 mBt; f_T =200 MFu; R_1/R_2 =10/47 kOm	SOT346,SC59	
Ή-	2SC4899	REN	npn	V _{CB0} =15 B; I _C =20 мA; P _D =100 мВт; h ₂₁ =50250; f _T >6ГГц	SOT323,SC70	
1	RN2108	TOSH	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =100 mBT; f_T =250 MF $_H$; R_1/R_2 =22/47 кОм	SOT416,SC75A	
1	RN2108F	TOSH	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBT; I_T =250 M Γ u; P_1/P_2 =22/47 kOm	SOT490,SC89	B-E-C
1	RN2108FT	TOSH	Dpnp	V _{CB0} =50 B; I _C =100 мA; P _D =100 мВт; f _T =250 МГц; R ₁ /R ₂ =22/47 кОм	TESM	B-E-C
1	RN2308	TOSH	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =100 mBt; f_T =200 MFi,; R_1/R_2 =22 kOm/47 kOm	SOT323,SC70	B-E-C
/1	RN2408	TOSH	Dpnp	V_{CEO} = 50 B; I_C = 100 mA; P_O = 200 mBt; f_T = 200 MFu; R_1/R_2 = 22/47 кОм	SOT346,SC59	B-E-C
/J	RN2109	TOSH	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBt; I_T =250 M Γ u; R_1/R_2 =47/22 kOm	SOT416,SC75A	B-E-C
/J	RN2109F	TOSH	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =100 mBt; f_T =250 MFu; R_1/R_2 =47/22 kOm	SOT490,SC89	B-E-C
/J	RN2109FT	TOSH	Dpnp	V_{CB0} =50 B; I_C =100 mA; P_D =100 mBt; f_T =250 MFu; R_1/R_2 =47/22 kOm	TESM	B.E.C
/J	RN2309	TOSH	Dpnp	V _{CB0} =50 B; I _C = 100 мА; P _D =100 мВт; f _T =200 МГц; R ₁ /B ₂ =47 кОм/22 кОм	SOT323,SC70	B·E·C
/J	RN2409	TOSH	Dpnp	V _{CEO} =50 B; I _C =100 mA; P _O =200 mBt; f _T =200 MFu; R ₁ /R ₂ =47/22 кОм	SOT346,SC59	B·E·C
/K	RN2110	TOSH	Donp	V _{сво} =50 B; I _C =100 мА; P _D =200 мВт; Г _Т =250 МГц; R ₁ =4.7 кОм	SOT416,SC75A	B-E-C
/K	RN2110F	TOSH	Dpnp	V _{GB0} =50 B; I _C =100 мА; P _D =100 мВт; f _T =250 МГц; R ₁ =4.7 кОм	SOT490,SC89	B-E-C
/K	RN2110FT	TOSH	Dono	V _{CR0} =50 B; I _C =100 мA; P _D =100 мВт; f _T =250 МГц; R ₁ =4.7 кОм	TESM	B·E·C
/K	RN2310	TOSH	Dpnp	V _{GB0} =50 B; I _G =100 мА; P _D =100 мВт; f _T =200 МГц; R ₁ =4.7 кОм	SOT323,SC70	B·E·C
/K	RN2410	TOSH	Donp	V _{ccn} =50 B; I _c =100 мА; P _o =200 мВт; f _T =20 МГц; R ₁ =4.7 кОм	SOT346.SC59	B-E-C
/K-	2SC4901	REN	non	V _{GB0} =15 B; I _C =50 мА; Р ₀ =150 мВт; h ₂₁ =50250; f _T >6ГГц	SOT323.SC70	B-E-C
/L-	2SC4902	REN	npn	V _{CP0} =20 B; I _C =30 mA; P _D =150 mBτ; h ₂₁ =50250; f _T >4ΓΓц	SOT23,SOD23	
/L-	2SC4903	REN	non	V _{CB0} =20 B; I _C =30 mA; P _D =150 mBτ; h ₂₁ =50250; f _T >4ΓΓц	SOT323.SC70	
/M	RN2111	TOSH	Dpnp	V _{CB0} =50 B; I _C =100 MA; P _D =200 MB; f _T =250 MFu; R ₁ =10 KOM	SOT416,SC75A	
/M	RN2111F	TOSH	Dono	V _{CB0} =50 B; I _C =100 MA; P _D =100 MBT; F _T =250 MFц; R ₁ =10 KOM	SOT490.SC89	
M	RN2111FT	TOSH	Donp	V _{CR0} =50 B; I _C =100 mA; P _D =100 mB _T ; F _T =250 MF _U ; R _T =10 kOm	TESM	B·E·C
M	RN2311	TOSH	Dono	V _{CBD} =50 B; I _C =100 мA; P _D =100 мB; f _T =200 МГц; R ₁ =10 кОм	SOT323,SC70	
M	RN2411	TOSH	Dono	V _{CF0} =50 B; I _C =100 MA; P _D =100 MB; f _T =200 MFu; R _T =10 KOM	SOT346.SC59	100000000000000000000000000000000000000
/N	RN2112	TOSH	Dono	V _{CBD} =50 B; I _C =100 MA; P _D =200 MB1; I _T =200 MIQ; R ₁ =10 KOM V _{CBD} =50 B; I _C =100 MA; P _D =200 MB1; I _T =250 MIQ; R ₁ =22 KOM	SOT416.SC75A	
/N	RN2112F	TOSH	Dono	V _{CB0} =50 B; I _C =100 MA; P _D =200 MB; F _T =250 MFц; R _T =22 κOM	SOT490.SC89	
/N	RN2112FT	TOSH			TESM	B-E-C
			Dpnp	V _{CB0} =50 B; I _C =100 mA; P _D =100 mB; f _T =250 MΓц; R ₁ =22 κOm		
N N	RN2312	TOSH	Dpnp	V _{CB0} =50 B; I _C =100 mA; P _D =100 mBr; f _T =200 MFu; R ₁ =22 kOm	SOT323,SC70	
N.	RN2412 2SD1484KP	TOSH	Dpnp npn	V_{CB0} *50 B; I_C *100 mA; P_D *200 mBT; f_T *200 MFU; R_T *22 KOM V_{CB0} *50 B; I_C *500 mA; P_D *200 mBT; h_{21} *82180; f_T >250 MFU	SOT346,SC59	
/P					SOT346,SC59	





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
/P	RN2113	TOSH	Dpnp	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBT; f _T =250 MFu; R _T =47 kOm	S0T416,SC75A	B·E·C
/P	RN2113F	TOSH	Dono	V _{CB0} =50 B; I _C =100 мА; P _D =100 мВт; f _T =250 МГц; R ₁ =47 кОм	SOT490,SC89	B·E·C
P	RN2113FT	TOSH	Dono	V _{CB0} =50B; I _C =100 мА; P _D =100 мВт; f _T =250 МГц; R ₁ =47 кОм	TESM	B·E·C
/P	RN2313	TOSH	Dono	V _{CR0} =50B; I _C =100 MA; P _D =100 MBT; f _T =200 MΓμ; R ₁ =47 κOM	SOT323.SC70	B·E·C
/P	RN2413	TOSH	Dono	V _{CF0} =50B;I _C =100 mA;P _D =200 mBT;f _T =200 MFu;R ₁ =47 kOm	SOT346,SC59	B·E·C
(0	2SD1484KQ	ROHM	non	V _{CR0} =50 B; I _C =500 MA; P _D =200 MBT; h ₂₄ =120270; f _T >250 MFu	SOT346.SC59	100000000000000000000000000000000000000
YO.	2SD1949Q	ROHM	non	V _{CB0} =50B; I _C =500 MA; P _D =200 MBr; h ₂₁ =120270; f _T >250 MFu	S0T323,SC70	-
YQ	BN2114	TOSH	Donio	V _{CR0} =50B; I _C =100 MA; P _D =100 MBT; f _T =200 MFu; R ₁ /R ₂ =1 KOM/10 KOM	S0T416.SC75A	
YQ	RN2314	TOSH	Dono	V _{CR0} =50B; I _C =100 MA; P _D =100 MBT; I _T =200 MFu; R ₁ /R ₂ =1 kOM/10 kOM	S0T323,SC70	
YO.	PN2414	TOSH	Dono	V _{CS0} *50B;I _C *100 MA;P _D *100 MB; f _T *200 MFu;R ₁ /R ₂ *1/10 KOM	SOT346,SC59	
/R	2SD1484KR	ROHM	non	V _{CB0} =50B; I _C =500 MA; P _D =200 MB; h ₂ =180390; f ₇ >250 MF _Q	SOT346,SC59	
rR	2SD1949R	ROHM	non		S0T323,SC70	1001/25/1991
rR			140.0	V _{CB0} =50B; I _C =500 мА; Р _D =200 мВт; h ₂₁ =180390; f _T >250 МГц		100000000000000000000000000000000000000
	MSD601R	MOT	npn	V _{CB0} =25B	SOT346,SC59	2007/31/2009
rs	MSD601S	MOT	npn	V _{C80} =25B	SOT346,SC59	
YS .	RN2115	TOSH	Dpnp	V _{CB0} =50 B; I _C =100 mA; P _D =100 mBT; f _T =200 MTu; R ₁ /R ₂ =2.2 κOm/10 κOm	SOT416,SC75A	
YS.	RN2315	TOSH	Dpnp	V_{CB0} =50B; I_C =100 mA; P_D =100 mBt; f_T =200 MFu; R_1/R_2 =2.2 kOm/10 kOm	SOT323,SC70	
YS.	RN2415	TOSH	Dpnp	V _{CEO} =50 B;I _C =100 mA;P _D =200 mBT;F _T =200 MFц;R ₁ /R ₂ =2.2/10 kOm	SOT346,SC59	
ΥT	RN2116	TOSH	Dpnp	V _{CB0} =50 B; I _C =100 mA; P ₀ =100 mBτ; f _T =200 MΓu; R ₁ /R ₂ =4.7 κOm/10 κOm	S0T416,SC75A	
ΥT	RN2316	TOSH	Dpnp	V _{CB0} =50 B; I _C =100 мA; P _D =100 мВт; f _T =200 МГц; R ₁ /R ₂ =4.7 кОм/10 кОм	SOT323,SC70	
1	RN2416	TOSH	Dpnp	V_{CE0} =50B; I_C =100 mA; P_0 =200 mB τ ; f_{τ} =200 M Γ u; R_1/R_2 =4.7/10 kOm	SOT346,SC59	B·E·C
/U	RN2117	TOSH	Dpnp	V_{CB0} =50B; I_C =100 mA; P_0 =100 mBr; f_T =200 M Γ u; R_1/R_2 =10 kOm/4.7 kOm	S0T416,SC75A	B·E·C
/U	RN2317	TOSH	Dpnp	V _{CB0} =50B; I _C =100 mA; P ₀ =100 mBt; f _T =200 MTu; R ₁ /R ₂ =10 κOm/4.7 κOm	SOT323,SC70	B·E·C
/U	RN2417	TOSH	Dpnp	V _{CEO} =50B;I _C =100 mA;P _D =200 mBT;f _T =200 MFu;R ₁ /R ₂ =10/4.7 кОм	SOT346,SC59	B·E·C
N-	2SC4964	REN	non	V _{CR0} =12B; I _C =100 mA; P _D =150 mBT; h ₂₄ =100600	SOT23,SOD23	B·E·C
W-	2SC4965	REN	non	V _{CB0} =12B; I _C =100 mA; P _D =100 mBr; h ₂₁ =100600	SOT323,SC70	B·E·C
W	RN2118	TOSH	Dono	V _{CR0} =50B; I _C =100 mA; P _D =100 mBT; f _T =200 MFu; R ₁ /R ₂ =47 kOm/10 kOm	S0T416,SC75A	B·E·C
W	RN2318	TOSH	Dono	V _{CB0} =50B; I _C =100 mA; P _D =100 mBT; f _T =200 MFц; R ₁ /R ₂ =47 кОм/10 кОм	SOT323.SC70	B·E·C
W	PN2418	TOSH	Dono	V _{CEO} =50 B ₁ I _C =100 MA; P _D =200 MBτ; f _T =200 MΓu; R ₁ /R ₂ =47/10 κOM	SOT346.SC59	B·E·C
YY1	CMPZDA11V	CSI	dz×2	$V_Z(I_{ZT}=5 \text{ MA})=10.411.6 \text{ B}; I_L(V_B=8.0 \text{ B}) \le 0.1 \text{ MKA}; Z_{ZT}(I_{ZT}=5.0 \text{ MA}) \le 20 \text{ OM}; I_{ZM}=15 \text{ MA}$	SOT23,SOD23	K2•K1•A2,A
YY2	CMPZDA12V	CSI	dz×2	$V_Z(I_{ZT}$ =5mA)=11.412.7B; $I_L(V_R$ =8.0B)<0.1 mkA; $Z_{ZT}(I_{ZT}$ =5.0 mA)<25 Om; I_{ZM} =13 mA	SOT23,SOD23	K2•K1•A2,4
YY3	CMPZDA13V	CSI	dz×2	$V_Z(I_{ZT}$ = 5 MA) = 12.414.1 B; $I_L(V_R$ = 8.0 B) < 0.1 MKA; $Z_{ZT}(I_{ZT}$ = 5.0 MA) < 30 OM; I_{ZM} = 12 MA	SOT23,SOD23	K2•K1•A2,A
YY4	CMPZDA15V	CSI	dz×2	$V_Z(I_{ZT}^-5 \text{ mA}) = 13.815.6 \text{ B}; I_1(V_B^-10.5 \text{ B}) \le 0.05 \text{ mrA}; $ $Z_Z(I_{ZT}^-5.0 \text{ mA}) \le 30.0 \text{ m; } I_{ZM}^-11 \text{ mA}$	SOT23,SOD23	K2•K1•A2,A
175	CMPZDA16V	CSI	dz×2	$\begin{array}{l} V_Z(I_{ZT}\!\!=\!5\text{MA})\!\!=\!15.317.1B;I_1\{V_B\!\!=\!11.2B\}\!\!\leq\!\!0.05\text{m/A};\\ Z_{ZT}(I_{ZT}\!\!=\!5.0\text{MA}\}\!\!\leq\!40\text{Om};I_{ZM}\!\!=\!10\text{MA} \end{array}$	SOT23,SOD23	0,000,000,000,000
YY6	CMPZDA18V	CSI	dz×2	$V_Z(I_{ZT}^-5 \text{ MA})^+16.819.1 \text{ B; } I_1(V_{B}^-12.6 \text{ B}) \le 0.05 \text{ m/A;} $ $Z_{ZT}(I_{ZT}^-5.0 \text{ MA}) \le 45 \text{ Om; } I_{ZM}^-9.2 \text{ MA}$	SOT23,SOD23	
Y 77	CMPZDA20V	CSI	dz×2	$V_Z(I_{ZT}$ =5 mA)=18.821.2B; $I_1(V_B$ =14.0B}<0.05 mrA; $Z_{ZT}(I_{ZT}$ =5.0 mA)<55 0 m; I_{ZM} =8.3 mA	SOT23,SOD23	
178	CMPZDA22V	CSI	dz×2	$\begin{array}{l} V_Z(I_{ZT}\!\!=\!5\text{MA})\!\!=\!\!20.823.3B;I_L(V_B\!\!=\!\!15.4B)\!<\!0.05\text{mkA};\\ Z_{ZT}(I_{ZT}\!\!=\!\!5.0\text{MA})\!<\!55\text{Om};I_{ZM}\!\!=\!\!7.6\text{mA} \end{array}$	SOT23,SOD23	
179	CMPZDA24V	CSI	dz×2	$V_Z(I_{ZT}^-5 \text{ MA})^+22.825.6B; I_1(V_B^+16.8B) \le 0.05 \text{ mkA}; $ $Z_{ZT}(I_{ZT}^-5.0 \text{ MA}) \le 70 \text{ Dm; } I_{ZM}^-7.0 \text{ MA}$	SOT23,SOD23	
/Z-	2SC5050	REN	npn	V _{CB0} =15 B; I _C =50 мА; P _D =150 мВт; h ₂₁ =50250; f _T >8 ГГц	SOT23,SOD23	
YZ-	2SC5051	REN	npn	V _{CB0} =15B; I _C =50 мA; P _D =100 мВт; h ₂₁ =50250; f _T >8 ГГц	SOT323,SC70	B·E·C
/Z-	2SC5544	REN	npn	V _{CBO} =15B; I _C =50 мА; P _D =80 мВт; h ₂₁ =85170; f _T >3 ГГц	SC81,MFPAK	C-B-E
20	SST310	SIL	nFET	V _{DS} =25 B;P _D =350 mBt;I _{DSS} =2460 mA;Q _F =10 mCm	SOT23,SOD23	D·S·G
Z1	BZX84C4V7	ALLEG	dz	V ₂ (I ₂₇ = 5 mA) = 4.45.0 B;I ₁ (V _B = 2.0 B) < 3.0 m;A; Z ₂₇ (I ₂₇ = 5 mA) < 80 Om	SOT23, SOD23	A·n.c.·K
Z1	BZX84C4V7	CSI	dz	V ₂ (I _{ZT} = 5 mA) = 4.45.0 B; I ₁ {V _B = 2.0 B} < 3.0 m; A; Z _{ZT} (I _{ZT} = 5 mA) < 80 Om; I _{ZM} < 53 mA	SOT23,SOD23	100000000000000000000000000000000000000
21	BZX84C4V7	VISH	dz	V _Z (I _{ZT} =5 MA)=4.45.0 B;Z _{ZT} (I _{ZT} =5 MA) < 80 OM	SOT23.SOD23	A·n.c·K

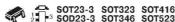
Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
21	BZX84C4V7LT1	MOT	dz	V ₂ (I _{ZT} =5mA)=4.45.0B;Z _{ZT} (I _{ZT} =5mA)<80 Om	SOT23,SOD23	A·n.c.·K
21	RN2357	TOSH	Dono	V _{CB0} =50 B; I _C =100 мА; P _D =100 мВт; f _T =200 МГц; R ₁ /R ₂ =10 кОм/47 кОм	SOT323,SC70	B·E·C
1	SSTJ211	SIL	nFET	V _{DS} =25B;P _D =350mBt;I _{DSS} >7mA; g _E >6mCm	SOT23,SOD23	D·S·G
211	BZX84C2V4	PHIL	dz	$V_2(I_{ZT}=5.0 \text{ MA})=2.22.6B; I_2(V_B=1.0 \text{ B}) \le 50 \text{ MKA}; Z_{ZT}(I_{ZT}=5.0 \text{ MA}) \le 100 \text{ OM}; I_{ZM}=200 \text{ MA}$	SOT23,SOD23	A•n.c.•K
211	BZX84C2V4LT1	MOT	dz	$V_Z(I_{ZT}=5.0 \text{ mA})=2.22.6 \text{ B; }I_L(V_R=1.0 \text{ B}) \le 50 \text{ mKA; }Z_{ZT}(I_{ZT}=5.0 \text{ mA}) \le 100 \text{ Om; }I_{ZM}=200 \text{ mA}$	SOT23,SOD23	A•n.c.•K
212	BZX84C2V7	PHIL	dz	$\frac{V_Z(I_{Z1}\!=\!5.0~\text{mA})\!=\!2.52.9~\text{B;}~I_L(V_R\!=\!1.0~\text{B})\!\leq\!20~\text{mkA;}~Z_{Z1}(I_{Z1}\!=\!5.0~\text{mA})\!\leq\!100~\text{Om;}}{I_{ZM}\!=\!200~\text{mA}}$	SOT23,SOD23	A·n.c.·K
12	BZX84C2V7	VISH	dz	V ₂ (I _{ZT} =5mA)=2.512.89B; Z _{ZT} (I _{ZT} =5mA)<100 Om	SOT23,SOD23	A·n.c.·K
213	BZX84C3V0	PHIL	dz	$V_Z(I_{ZT}$ =5.0 mA)=2.83.2 B; $I_L(V_B$ =1.0 B) < 10 mKA; $Z_{ZT}(I_{ZT}$ =5.0 mA) < 95 Om; I_{ZM} =200 mA	SOT23,SOD23	A•n.c.•K
213	BZX84C3V0	VISH	dz	V _Z (I _{ZT} =5.0 mA)=2.83.2B; Z _{ZT} (I _{ZT} =5.0 mA) < 100 Om	SOT23,SOD23	A·n.c.·K
213	BZX84-C3V0LT1	MOT	dz	V _Z (I _{ZT} =5.0 mA)=2.83.2 B; Z _{ZT} (I _{ZT} =5.0 mA) < 100 Om	SOT23,SOD23	A·n.c.·K
214	BZX84C3V3	PHIL	dz	$V_Z(I_{ZT}$ =5.0 mA)=3.13.5 B; $I_L(V_B$ =1.0 B) <5 mKA; $Z_{ZT}(I_{ZT}$ =5.0 mA) <95 Om; I_{ZM} =200 mA	SOT23,SOD23	A•n.c.•K
214	BZX84C3V3	VISH	dz	V _Z (I _{ZT} =5mA)=3.13.5B;Z _{ZT} (I _{ZT} =5mA)<95 Om	SOT23,SOD23	
215	BZX84C3V6	PHIL	dz	$\begin{array}{l} V_2(I_{ZT}\!=\!5.0\text{ mA})\!=\!3.43.8\text{ B; }I_L(V_R\!=\!1.0\text{ B})\!<\!5\text{mKA; }Z_{ZT}(I_{ZT}\!=\!5.0\text{ mA})\!<\!90\text{ Om; }\\ I_{ZM}\!=\!200\text{mA} \end{array}$	SOT23,SOD23	A·n.c.·K
215	BZX84C3V6	VISH	dz	$V_2(I_{ZT}=5 \text{ mA})=3.43.8 \text{ B}; Z_{ZT}(I_{ZT}=5 \text{ mA})<95 \text{ Om}$	SOT23,SOD23	
216	BZX84C3V9	PHIL	dz	$\begin{array}{l} V_Z(I_{ZT}\!\!=\!5.0\text{ mA})\!\!=\!\!3.74.1\text{ B}; I_L(V_B\!\!=\!\!1.0\text{ B})\!\!<\!\!3\text{mKA}; Z_{ZT}(I_{ZT}\!\!=\!\!5.0\text{ mA})\!\!<\!\!90\text{ Om}; \\ I_{ZM}\!\!=\!\!200\text{mA} \end{array}$	SOT23,SOD23	NEI OTHER MAN
216	BZX84C3V9	VISH	dz	V ₂ (I _{ZT} =5mA)=3.74.1B;Z _{ZT} (I _{ZT} =5mA)<90 Om	SOT23,SOD23	
217	BZX84C4V3	PHIL	dz	$\begin{array}{l} V_Z(I_{ZT}\!=\!5.0\text{ mA})\!=\!4.04.6\text{ B; }I_L(V_B\!=\!1.0\text{ B})\!\leq\!3\text{ mKA; }Z_{ZT}(I_{ZT}\!=\!5.0\text{ mA})\!\leq\!90\text{ Om; }\\ I_{ZM}\!=\!200\text{ mA} \end{array}$	SOT23,SOD23	
217	BZX84C4V3	VISH	dz	V _Z (I _{ZT} =5 mA)=4.04.6 B; Z _{ZT} (I _{ZT} =5 mA) < 90 Om	SOT23,SOD23	
1A	BC846A	ZETEX	npn	V_{CB0} =80 B; I_C =100 mA; P_D =330 mBt; h_{21} =110220; f_T >300 MF $_{4}$	SOT23,SOD23	
1E	BC847A	ZETEX	npn	V_{CB0} =50 B; I_C =100 mA; P_D =330 mBt; h_{21} =110220; f_T >300 M Γ_{II}	SOT23,SOD23	
21L	BC848C	ZETEX	npn	V_{GB0} =30 B; I_C =100 mA; P_D =330 mBT; h_{21} =420800; f_T >300 MF $_{II}$	SOT23,SOD23	
21p	BZX84C4V7	PHIL	dz	$\begin{array}{l} V_Z(I_{ZT}\!\!=\!5.0\text{ mA})\!\!=\!4.45.0\text{ B}; I_L(V_B\!\!=\!\!2.0\text{ B})\!\!\leq\!\!3\text{mKA}; Z_{ZT}(I_{ZT}\!\!=\!\!5.0\text{ mA})\!\!\leq\!\!80\text{ Om}; \\ I_{ZM}\!\!=\!\!200\text{mA} \end{array}$	SOT23,SOD23	A·n.c.·K
Z1t	BZX84C4V7	PHIL	dz	$\begin{array}{l} V_Z(I_{ZT}\!\!=\!5.0\text{ mA})\!\!=\!4.45.0\text{ B; }I_L(V_B\!\!=\!\!2.0\text{ B})\!\!<\!\!3\text{mKA; }Z_{ZT}(I_{ZT}\!\!=\!\!5.0\text{ mA})\!\!<\!\!80\text{ Om;}\\ I_{ZM}\!\!=\!\!200\text{mA} \end{array}$	SOT23,SOD23	A•n.c.•K
22	BZX84C5V1	ALLEG	dz	$V_2(I_{ZT}=5 \text{ mA})=4.85.4 \text{ B}; I_1(V_R=2.0 \text{ B}) \le 2.0 \text{ m/sA}; Z_{ZT}(I_{ZT}=5 \text{ mA}) \le 60 \text{ Om}$	SOT23,SOD23	
22	BZX84C5V1	CSI	dz	$V_Z(I_{ZT}$ = 5 MA} = 4.85.4 B; $I_L(V_B$ = 2.0 B) < 2.0 MKA; $Z_{ZT}(I_{ZT}$ = 5 MA) < 60 O M; I_{ZM} < 49 MA	SOT23,SOD23	
22	BZX84C5V1	VISH	dz	V _Z (I _{ZT} =5 mA)=4.85.4 B; Z _{ZT} (I _{ZT} =5 mA)<60 Om	SOT23,SOD23	
2	SSTJ212	SIL	nFET	V _{DS} =25B;P _D =350 мВт;I _{DSS} >15 мА; g _F >7 мСм	SOT23,SOD23	
21	DTC113ZE	ROHM	Dnpn	V_{GB0} =50 B; I_C =100 mA; P_D =150 mBT; h_{21} >33; f_T >250 MFu; R_1/R_2 =1/10 кOm	SOT416,SC75A	
21	DTC113ZKA	ROHM	Dnpn	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBt; h_{21} >33; f_T >250 MFu; R_1/R_2 =1/10 кOm	SOT346,SC59	
21	DTC113ZUA	ROHM	Dnpn	V_{CB0} =50 B; I_C =100 mÅ; P_D =200 mBt; h_{21} >33; f_T >250 MFu; R_1/R_2 =1/10 кOm	SOT323,SC70	
22G	BC850C	ZETEX	npn	V_{CB0} =50 B; I_C =100 mA; P_D =330 mBr; h_{21} =420800; f_T >300 M Γ_U	SOT23,SOD23	
22p	BZX84C5V1	PHIL	dz	$\frac{V_2(I_{ZT}\text{=-}5.0 \text{ mA})\text{=-}4.85.4B; I_L(V_R\text{=-}2.0B)\text{<-}2 \text{mKA; } Z_{ZT}(I_{ZT}\text{=-}5.0 \text{ mA})\text{<-}60 \text{ OM; }}{I_{ZM}\text{=-}200 \text{mA}}$	SOT23,SOD23	100000000000000000000000000000000000000
22t	BZX84C5V1	PHIL	dz	$\begin{array}{l} V_Z(I_{ZT}\!=\!5.0\text{ mA})\!=\!4.85.4\text{ B; }I_L(V_R\!=\!2.0\text{ B})\!\leq\!2\text{nikA; }Z_{ZT}(I_{ZT}\!=\!5.0\text{ mA})\!\leq\!60\text{ Cm; }\\ I_{ZM}\!=\!200\text{ mA} \end{array}$	SOT23,SOD23	
22U	FMMTA63	ZETEX	pnp	V_{CB0} =30 B; I_C =500 mA; P_D =330 mBT; h_{21} =10000; f_T >125 MF $_{II}$	SOT23,SOD23	
2∀	FMMTA64	ZETEX	pnp	V_{CB0} =30 B; I_C =500 MA; P_D =330 MB1; h_{21} =20000; f_T >125 M Γ_{II}	SOT23,SOD23	
3	BZX84C5V6	ALLEG	dz	$V_z(I_{ZT}=5\text{ mA})=5.26.0\text{ B}; I_L(V_R=2.0\text{ B}) \le 1.0\text{ mKA}; Z_{ZT}(I_{ZT}=5\text{ mA}) \le 400\text{ m}$	SOT23,SOD23	107751000000000000000000000000000000000
23	BZX84C5V6	CSI	dz	$V_{z}(I_{zT}=5\text{ mA})=5.26.0\text{ B}; I_{\underline{t}}(V_{R}=2.0\text{ B})<1.0\text{ m/s}; Z_{zT}(I_{zT}=5\text{ mA})<40\text{ Om}; I_{ZM}<45\text{ mA}$	SOT23,SOD23	
23	BZX84C5V6	VISH	dz	V ₂ (I _{ZT} =5mA)=5.26.0B;Z _{ZT} (I _{ZT} =5mA)<40 Om	SOT23,SOD23	
3B	BC856B	ZETEX	pnp	V_{CB0} =80 B; I_C =100 mA; P_D =330 mBr; h_{21} =220475; f_T >150 M Γ_U	SOT23,SOD23	DC2/811 (20)
23E	BC857A	ZETEX	pnp	V_{CB0} =50 B; I_C =100 mA; P_D =330 mBt; h_{21} =125250; f_T >150 M Γ_H	SOT23,SOD23	
Z3p	BZX84C5V6	PHIL	dz	$V_Z(I_{ZT}=5.0 \text{ mA})=5.26.0 \text{ B}; I_L(V_B=2.0 \text{ B}) \le 1 \text{ mrA}; Z_{ZT}(I_{ZT}=5.0 \text{ mA}) \le 40 \text{ Om}; I_{ZM}=200 \text{ mA}$	SOT23,SOD23	A•n.c.•K





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3
Z3t	BZX84C5V6	PHIL	dz	$V_Z(I_{ZT}$ = 5.0 mA) = 5.26.0 B; $I_L(V_R$ = 2.0 B) < 1 mkA; $Z_{ZT}(I_{ZT}$ = 5.0 mA) < 40 0 m; I_{ZM} = 200 mA	SOT23,SOD23	A•n.c.•K
24	BZX84C6V2	ALLEG	dz	V _Z (I _{ZT} =5 mA)=5.86.6 B;I _L (V _R =4.0 B)<3.0 m;A;Z _{ZT} (I _{ZT} =5 mA)<10 0 m	SOT23,SOD23	A+n.c.+K
Z4	BZX84C6V2	CSI	dz	$V_{Z}(I_{ZT}=5 \text{ mA})=5.86.6 \text{ B}; I_{L}\{V_{R}=4.0 \text{ B}\} \le 3.0 \text{ m/A}; Z_{ZT}\{I_{ZT}=5 \text{ mA}\} \le 100 \text{ m}; I_{ZM} \le 40 \text{ mA}$	SOT23,SOD23	A•n.c.•K
Z4	BZX84C6V2	VISH	dz	V _Z (I _{ZT} =5 MA)=5.86.6 B;Z _{ZT} (I _{ZT} =5 MA) < 10 OM	SOT23,SOD23	A·n.c.•K
Z4A	BC859A	ZETEX	pnp	V _{CB0} =30B; I _C =100 мА; P _D =330 мВт; h ₂₁ =125250; f _T >300 МГц	SOT23,SOD23	B·E·C
Z4C	BC859C	ZETEX	pnp	V _{CB0} =30 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =420800; f _T >300 МГц	SOT23,SOD23	B·E·C
Z4E	BC860A	ZETEX	pnp	V _{CB0} =50 B; I _C =100 мА; P _D =330 мВт; h ₂₁ =125250; f _T >300 МГц	SOT23,SOD23	B·E·C
Z4 p	BZX84C6V2	PHIL	dz	$V_Z(I_{ZT}$ = 5.0 mA) = 5.86.6 B; $I_L(V_R$ = 4.0 B) < 3 mkA; $Z_{ZT}(I_{ZT}$ = 5.0 mA) < 10 0 m; I_{ZM} = 200 mA	SOT23,SOD23	A+n.c.+K
Z4t	BZX84C6V2	PHIL	dz	$V_{Z}(I_{ZT}=5.0 \text{ mA})=5.86.6 \text{ B}; I_{L}(V_{R}=4.0 \text{ B}) \le 3 \text{m/sA}; Z_{ZT}(I_{ZT}=5.0 \text{ mA}) \le 10 0 \text{m}; I_{ZM}=200 \text{ mA}$	SOT23,SOD23	A•n.c.•K
Z5	BZX84C6V8	ALLEG	dz	V _Z (I _{ZT} =5 MA)=6.47.2B;I _L (V _R =4.0 B)<2.0 MrA;Z _{ZT} (I _{ZT} =5 MA)<150 M	SOT23,SOD23	A·n.c.•K
Z 5	BZX84C6V8	CSI	dz	$V_z(I_{ZT} = 5 \text{ mA}) = 6.47.2 \text{ B}; I_z(V_B = 4.0 \text{ B}) \le 2.0 \text{ m/A}; Z_{ZT}(I_{ZT} = 5 \text{ mA}) \le 150 \text{ m}; I_{ZM} \le 37 \text{ mA}$	SOT23,SOD23	Arn.c.•K
Z5	BZX84C6V8	VISH	dz	V _Z (I _{ZT} = 5 мA) = 6.47.2 B; Z _{ZT} (I _{ZT} = 5 мA) < 15 Om	SOT23,SOD23	A+n.c.+K
Z50	BZX84B2V4	PHIL	dz	$V_{Z}(I_{ZT}=5 \text{ MA})=2.42.5 \text{ B}, I_{L}V_{R}=1.0 \text{ B}) < 50 \text{ M/A}; Z_{ZT}(I_{ZT}=5.0 \text{ MA}) < 100 \text{ OM}; I_{ZM}=200 \text{ MA}$	SOT23,SOD23	A•n.c.•K
Z51	BZX84B2V7	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ mA}) = 2.682.75 \text{ B}; I_L(V_R = 1.0 \text{ B}) \le 20 \text{ mKA}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) \le 100 \text{ Om}; I_{ZM} = 200 \text{ mA}$	SOT23,SOD23	A•n.c.•K
Z52	BZX84B3V0	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ in A}) = 2.94 \dots 3.06 \text{ B}; I_L(V_R = 1.0 \text{ B}) \le 10 \text{ in KA}; Z_{ZT}(I_{ZT} = 5.0 \text{ in A}) \le 95 \text{ Om}; I_{ZM} = 200 \text{ in A}$	SOT23,SOD23	A-n.cK
Z53	BZX84B3V3	PHIL	dz	$V_Z(I_{ZT}=5 \text{ MA})=3.233.37 \text{ B}; I_L(V_R=1.0 \text{ B}) \le 5 \text{ M/KA}; Z_{ZT}(I_{ZT}=5.0 \text{ MA}) \le 950 \text{ M}; I_{ZM}=200 \text{ MÅ}$	SOT23,SOD23	A•n.c.•K
Z54	BZX84B3V6	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ MA}) = 3.533.67 \text{ B}; I_L(V_R = 1.0 \text{ B}) < 5 \text{ MKA}; Z_{ZT}(I_{ZT} = 5.0 \text{ MA}) < 90 \text{ Om}; I_{ZM} = 200 \text{ MA}$	SOT23,SOD23	A•n.c.•K
Z55	BZX84B3V9	PHIL	dz	V _Z (I _{ZT} = 5 MA) = 3.823.98 B; I _L (V _R = 1.0 B) < 3 MKA; Z _{ZT} (I _{ZT} = 5.0 MA) < 90 O M; I _{ZM} = 200 MA	SOT23,SOD23	A•n.c.•K
Z56	BZX84B4V3	PHIL	dz	V _Z (I _{ZT} *5 mA) *4.214.39B; I _L (V _B *1.0B) <3 mrA; Z _{ZT} (I _{ZT} *5.0 mA) < 90 0 m; I _{ZM} *200 mA	SOT23,SOD23	A•n.c.•K
Z57	BZX84B4V7	PHIL	dz	V _Z (I _{ZT} * 5 mA) * 4.614.79B; I _L (V _R * 2.0B) < 3 mrA; Z _{ZT} (I _{ZT} * 5.0 mA) < 80 Om; I _{ZM} * 200 mA	SOT23,SOD23	A+n.c.+K
Z58	BZX84B5V1	PHIL	dz	$V_Z(I_{ZT}=5 \text{ MA})=5.005.20 \text{ B; } I_L(V_R=2.0 \text{ B}) \le 2 \text{ MKA; } Z_{ZT}(I_{ZT}=5.0 \text{ MA}) \le 60 \text{ Om; } I_{ZM}=200 \text{ MA}$	S0T23,S0D23	A•n.c.•K
Z59	BZX84B5V6	PHIL	dz	V _Z (I _{ZT} =5.MA)=5.495.71B;I _L (V _R =2.0B)<1mkA;Z _{ZT} (I _{ZT} =5.0mA)<40.0m; I _{ZM} =200 mA	SOT23,SOD23	A•n.c.•K
Z5p	BZX84C6V8	PHIL	dz	$V_{Z}(I_{ZI} = 5 \text{ mA}) = 6.47.2 \text{ B}; I_{L}(V_{R} = 4.0 \text{ B}) \le 2 \text{ mrA}; Z_{ZI}(I_{ZI} = 5.0 \text{ mA}) \le 15 \text{ Om}; I_{ZM} = 200 \text{ mA}$	SOT23,SOD23	A•n.c.•K
Z5t	BZX84C6V8	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ inA}) = 6.47.2 \text{ B}; I_L(V_R = 4.0 \text{ B}) \le 2 \text{ m/A}; Z_{ZT}(I_{ZT} = 5.0 \text{ inA}) \le 15 \text{ Om}; I_{ZM} = 200 \text{ inA}$	SOT23,SOD23	A•n.c.•K
Z6	BZX84C7V5	ALLEG	dz	Vz(Izr=5 MA)=7.07.9 B;I ₁ (V _B =5.0 B)<1.0 MKA;Z _{ZT} (I _{ZT} =5 MA)<15 OM	SOT23,SOD23	A·n.c.·K
Z 6	BZX84C7V5	CSI	dz	$V_{\mathcal{L}}(I_{\mathcal{L}_T} = 5 \text{ in A}) = 7.07.9 \text{ B}; I_{\mathcal{L}}(V_R = 5.0 \text{ B}) \le 1.0 \text{ m/s}; Z_{\mathcal{L}}(I_{\mathcal{L}_T} = 5 \text{ in A}) \le 150 \text{ m}; I_{\mathcal{L}_M} \le 33 \text{ in A}$	SOT23,SOD23	A•n.c.•K
Z6	BZX84C7V5	VISH	dz	V _Z (I _{ZT} =5 MA)=7.07.9 B;Z _{ZT} (I _{ZT} =5 MA) < 15 OM	SOT23,SOD23	A·n.c.·K
Z60	BZX84B6V2	PHIL	dz	$V_{Z}(I_{ZT} = 5 \text{ MA}) = 6.086.32 \text{ B}; I_{L}(V_{R} = 4.0 \text{ B}) \le 3 \text{ MrA}; Z_{ZT}(I_{ZT} = 5.0 \text{ MA}) \le 10 \text{ DM}; I_{ZM} = 200 \text{ MA}$	SOT23,SOD23	Arn.c.rK
Z61	BZX84B6V8	PHIL	dz	V _Z (I _{ZT} = 5mA) = 6.666.94 B; I _L (V _B = 4.0 B) < 2mkA; Z _{ZT} (I _{ZT} = 5.0 mA) < 15 0m; I _{ZM} = 200 mA	SOT23,SOD23	A+n.c.+K
Z62	BZX84B7V5	PHIL	dz	$V_{\mathcal{L}}(I_{ZT} = 5 \text{ mA}) = 7.357.65 \text{ B}; I_{\mathcal{L}}(V_{\mathcal{R}} = 5.0 \text{ B}) \le 1 \text{ m/A}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) \le 15 \text{ Dm}; I_{ZM} = 200 \text{ mA}$	SOT23,SOD23	A•n.c.•K
Z63	BZX84B8V2	PHIL	dz	$V_Z(I_{ZT}$ = 5 MA) = 8.048.36 B; $I_L(V_B$ = 5.0 B) < 700 HA; $Z_{ZT}(I_{ZT}$ = 5.0 MA) < 15 Om; I_{ZM} = 200 MA	SOT23,SOD23	A•n.c.•K
Z64	BZX84B9V1	PHIL	dz	$V_Z(I_{ZT}=5 \text{ inA})=8.929.28 \text{ B; }I_L(V_B=6.0 \text{ B}) \le 500 \text{ inA; } Z_{ZT}(I_{ZT}=5.0 \text{ inA}) \le 150 \text{ in; } I_{ZM}=200 \text{ inA}$	SOT23,SOD23	A+n.c.+K
Z65	BZX84B10	PHIL	dz	$ Z_{Z} _{ZT} = 5 \text{ mA} = 9.8 10.2; I_{L}(V_{R} = 7.0 \text{ B}) \le 200 \text{ mA}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) \le 200 \text{ m}; I_{ZM} = 200 \text{ mA}$	SOT23,SOD23	A•n.c.•K

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3
Z66	BZX84B11	PHIL	dz	$V_2(I_{ZT}$ = 5MA) = 10.811.2B; $I_L(V_R$ = 8.0B} < 100 HA; $Z_{ZT}(I_{ZT}$ = 5.0 MA) < 20 OM; I_{ZM} = 200 MA	SOT23,SOD23	A·n.c.·K
Z67	BZX84B12	PHIL	dz	$V_2(I_{ZT} = 5 \text{ mA}) = 11.812.2 \text{ B}; I_2(V_B = 8.0 \text{ B}) < 100 \text{ mA}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 25 \text{ Om}; I_{ZM} = 200 \text{ mA}$	SOT23,SOD23	A·n.c.·K
Z68	BZX84B13	PHIL	dz	$V_2(I_{ZT}$ = 5mA) = 12.713.3B; $I_L(V_B$ = 8.0B} < 100 HA; $Z_{ZT}(I_{ZT}$ = 5.0 mA) < 30 Om; I_{ZM} = 200 mA	SOT23,SOD23	A•n.c.•K
Z69	BZX84B15	PHIL	dz	$V_2(I_{ZT}^-5MA)^+14.715.3B;I_1(V_{B}^-10.5B)<0.05MKA;$ $Z_{ZT}(I_{ZT}^-5.0MA)<300M;I_{ZM}^-200MA$	SOT23,SOD23	A·n.c.·K
Z6p	BZX84C7V5	PHIL	dz	$V_Z(I_{ZT} = 5MA) = 7.07.9B$; $I_L(V_R = 5.0B) \le 1 MKA$; $Z_{ZT}(I_{ZT} = 5.0 MA) \le 15 OM$; $I_{ZM} = 200 MA$	SOT23,SOD23	A·n.c.·K
Z6t	BZX84C7V5	PHIL	dz	$V_2(I_{ZT}^-5MA)^+7.07.9B;I_L(V_R^-5.0B) \le 1 MKA; Z_{ZT}(I_{ZT}^-5.0 MA) \le 15 OM;$ $I_{ZM}^-200 MA$	SOT23,SOD23	A·n.c.·K
27	BZX84C8V2	ALLEG	dz	$V_2(I_{ZT}=5 \text{ mA})=7.78.7 \text{ B}; I_1(V_{R}=5.0 \text{ B}) \le 0.7 \text{ m/s}; Z_{ZT}(I_{ZT}=5 \text{ mA}) \le 150 \text{ m}$	SOT23,SOD23	A•n.c.•K
Z 7	BZX84C8V2	CSI	dz	$V_2(I_{ZT}^-5MA)^-7.78.9B;I_2(V_R^-5.0B) \le 0.7 \text{ MKA}; Z_{ZT}(I_{ZT}^-5MA) \le 15 \text{ OM}; I_{ZM} \le 30 \text{ MA}$	SOT23,SOD23	A·n.c.·K
Z 7	BZX84C8V2	VISH	dz	V _Z (I _{ZT} =5mA)=7.78.9B;Z _{ZT} (I _{ZT} =5mA)<15 Om	SOT23,SOD23	A•n.c.•K
Z70	BZX84B16	PHIL	dz	$V_Z(I_{ZT}$ = 5mA) = 15.716.3B; $I_L(V_B$ = 11.2B) < 50 HA; $Z_{ZT}(I_{ZT}$ = 5.0 mA) < 40 Om; I_{ZM} = 200 mA	SOT23,SOD23	Arn.c.rK
Z71	BZX84B18	PHIL	dz	$V_2(I_{ZT}$ = 5MA) = 17.618.4 B; $I_L(V_B$ = 12.6 B) < 50 HA; $Z_{ZT}(I_{ZT}$ = 5.0 MA) < 45 OM; I_{ZM} = 200 MA	SOT23,SOD23	A·n.c.·K
Z72	BZX84B20	PHIL	dz	$V_Z(I_{ZT}$ = 5mA) = 19.620.4 B; $I_L(V_R$ = 14.0 B) < 50 HA; $Z_{ZT}(I_{ZT}$ = 5.0 mA) < 55 Om; I_{ZM} = 200 mA	SOT23,SOD23	A·n.c.·K
Z73	BZX84B22	PHIL	dz	$\frac{V_Z(I_{ZI}\text{-}5\text{MA})\text{-}21.622.4B;I_L(V_{R}\text{-}15.4B)\text{<}50\text{HA;}}{I_{ZM}\text{-}200\text{MA}}\text{<}221(I_{ZI}\text{-}5.0\text{MA})\text{<}55\text{Om;}}{I_{ZM}\text{-}200\text{MA}}$	SOT23,SOD23	A-n.cK
Z74	BZX84B24	PHIL	dz	$V_Z(I_{ZT}$ = 5MA) = 23.524.5B; $I_L(V_B$ = 16.8B) < 50 HA; $Z_{ZT}(I_{ZT}$ = 5.0 MA) < 30 OM; I_{ZM} = 250 MA	SOT23,SOD23	A·n.c.·K
Z75	BZX84B27	PHIL	dz	$V_2(I_{ZT}$ = 2mA) = 26.527.5B; $I_L(V_B$ = 18.9B) < 50 HA; $Z_{ZT}(I_{ZT}$ = 2.0 mA) < 80 Om; I_{ZM} = 200 mA	SOT23,SOD23	A·n.c.·K
Z76	BZX84B30	PHIL	dz	$V_Z(I_{ZT}$ = 2mA) = 29.430.6 B; $I_L(V_R$ = 21.0 B) < 50 HA; $Z_{ZT}(I_{ZT}$ = 2.0 mA) < 80 Om; I_{ZM} = 200 mA	SOT23,SOD23	A·n.c.·K
Z77	BZX84B33	PHIL	dz	$V_2(I_{ZT}$ = 2mA) = 32.333.7 B; $I_L(V_B$ = 23.1 B) < 50 HA; $Z_{ZT}(I_{ZT}$ = 2.0 mA) < 80 Om; I_{ZM} = 200 mA	SOT23,SOD23	A·n.c.·K
Z78	BZX84B36	PHIL	dz	$V_2(I_{ZT}^2 = 2MA)^2 = 35.336.7 B; I_1(V_B^2 = 25.2 B) \le 50 HA; Z_{ZT}(I_{ZT}^2 = 2.0 MA) \le 90 Om; I_{ZM}^2 = 200 MA$	SOT23,SOD23	A·n.c.·K
Z79	BZX84B39	PHIL	dz	$V_Z(I_{ZT}$ = 2mA) = 38.2 39.8 B; $I_L(V_B$ = 27.3 B) \leq 50 HA; $Z_{ZT}(I_{ZT}$ = 2.0 MA) \leq 75 OM; I_{ZM} = 250 MA	SOT23,SOD23	A·n.c.·K
Z7p	BZX84C8V2	PHIL	dz	$V_2(I_{ZT}$ =5MA)=7.78.7 B; $I_L(V_R$ =5.0 B) < 700 HA; $Z_{ZT}(I_{ZT}$ =5.0 MA) < 15 0M; I_{ZM} =200 MA	SOT23,SOD23	A•n.c.•K
Z7t	BZX84C8V2	PHIL	dz	$V_Z(I_{ZT}=5\text{MA})=7.78.7 \text{ B}; I_L(V_R=5.0 \text{ B}) \le 700 \text{ HA}; Z_{ZT}(I_{ZT}=5.0 \text{ MA}) \le 150 \text{ M}; I_{ZM}=200 \text{ MA}$	SOT23,SOD23	A·n.c.·K
Z8	BZX84C9V1	ALLEG	dz	$V_2(I_{ZT}=5 \text{ mA})=8.59.6 \text{ B}; I_1(V_R=6.0 \text{ B})<0.5 \text{ m/cA}; Z_{ZT}(I_{ZT}=5 \text{ mA})<150 \text{ m}$	SOT23,SOD23	A·n.c.·K
Z8	BZX84C9V1	CSI	dz	$V_2(I_{ZT}=5mA)=8.59.6B;I_L(V_R=6.0B)<0.5mkA;Z_{ZT}(I_{ZT}=5mA)<150m;I_{ZM}<27mA$	SOT23,SOD23	A·n.c.·K
Z8	BZX84C9V1	VISH	dz	V ₂ (I _{ZT} =5mA)=8.59.6B;Z _{ZT} (I _{ZT} =5mA)<15 Om	SOT23,SOD23	A·n.c.·K
Z8	SST308	SIL	nFET	V _{DS} =25 B; P _D =350 мВт; I _{DSS} =1260 мА; g _F =8 мСм	SOT23,SOD23	D·S·G
Z80	BZX84B43	PHIL	dz	$V_2(I_{ZT}^-2MA)^+42.143.9B; I_2(V_{B}^-30.1B) \le 50HA; Z_{ZT}(I_{ZT}^-2MA) \le 150OM; I_{ZM}^-200MA$	SOT23,SOD23	A·n.c.·K
Z81	BZX84B47	PHIL	dz	$V_2(I_{ZT} = 2mA) = 46.147.9B; I_1(V_B = 32.9B) \le 50 HA; Z_{ZT}(I_{ZT} = 2mA) \le 1700 m; I_{ZM} = 200 mA$	SOT23,SOD23	A·n.c.·K
Z82	BZX84B51	PHIL	dz	$V_Z(I_{ZT} = 2mA) = 50.052.0B; I_L(V_R = 35.7B) \le 50 HA; Z_{ZT}(I_{ZT} = 2mA) \le 1800 M; I_{ZM} = 200 MA$	SOT23,SOD23	A·n.c.·K
Z83	BZX84B56	PHIL	dz	$V_2(I_{ZT}^-2MA)^-54.957.1B;I_1(V_B^-39.2B) \le 50$ HA; $Z_{ZT}(I_{ZT}^-2MA) \le 200$ OM; I_{ZM}^-200 MA	SOT23,SOD23	A·n.c.·K
Z84	BZX84B62	PHIL	dz	$V_Z(I_{ZT}$ = 2mA) = 60.863.2B; $I_L(V_B$ = 43.4B) < 50 HA; $Z_{ZT}(I_{ZT}$ = 2mA) < 215 Om; I_{ZM} = 200 mA	SOT23,SOD23	A·n.c.·K
Z85	BZX84B68	PHIL	dz	$V_Z(I_{ZT}$ = 2mA) = 66.669.4 B; IL(V_R = 47.6 B) < 50 HA; $Z_{ZT}(I_{ZT}$ = 2mA) < 240 Om; I_{ZM} = 200 mA	SOT23,SOD23	A·n.c.·K
Z86	BZX84B75	PHIL	dz	$V_2(I_{ZT} = 2mA) = 73.576.5B; I_1(V_B = 52.5B) \le 50 \text{ HA}; Z_{ZT}(I_{ZT} = 2mA) \le 2550\text{m}; I_{ZM} = 200 \text{ mA}$	SOT23,SOD23	A·n.c.·K





Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3
Z8p	BZX84C9V1	PHIL	dz	$V_{Z}I_{ZT}=5$ mA)=859.6B; $I_{L}V_{R}=6.0$ B}<500 nA; $Z_{ZT}I_{LT}=5$ mA}<15 Om; $I_{ZM}=200$ mA	SOT23,SOD23	A+n.c.+K
Z8t	BZX84C9V1	PHIL	dz	$V_Z(I_{ZT} = 5 \text{ MA}) = 8.59.6 \text{ B}; I_L(V_B = 6.0 \text{ B}) \le 500 \text{ HA}; Z_{ZT}(I_{ZT} = 5 \text{ MA}) \le 15 \text{ OM}; I_{ZM} = 200 \text{ MA}$	SOT23,SOD23	A•n.c.•K
Z9	BZX84C10	ALLEG	dz	$V_Z(I_{ZT}=5 \text{ mA})=9.410.6 \text{ B}; I_L(V_R=7.0 \text{ B}) < 0.2 \text{ m/sA}; Z_{ZT}(I_{ZT}=5 \text{ mA}) < 20 \text{ OM}$	SOT23,SOD23	A+n.c.+K
Z 9	BZX84C10	VISH	dz	V _Z (I _{ZT} =5 mA)=9.410.6 B; Z _{ZT} (I _{ZT} =5 mA) < 20 Om	SOT23,SOD23	A+n.c.+K
Z9	SST309	SIL	nFET	V _{DS} =25 B;P _D =350 mBt;I _{DSS} =1230 mA; g _F =10 mCm	SOT23,SOD23	D·S·G
Z9p	BZX84C10	PHIL	dz	$V_Z(I_{ZT}=5 \text{ mÅ})=9.410.6; I_L(V_R=7.0 \text{ B}) \le 200 \text{ mÅ}; Z_{ZT}(I_{ZT}=5.0 \text{ mÅ}) \le 200 \text{ m}; I_{ZM}=200 \text{ mÅ}$	SOT23,SOD23	Arn.c.rK
Z9t	BZX84C10	PHIL	dz	$V_Z(I_{ZT}$ =5 MA)=9.410.6; $I_L(V_R$ =7.0B)<200 HA; $Z_{ZT}(I_{ZT}$ =5.0 MA)<20 OM; I_{ZM} =200 MA	SOT23,SOD23	Arn.c.rK
ZA6	FMMD2838	ZETEX	fid×2	$V_R < 75B$; $I_F < 100 \text{ mA}$; $V_F (I_F = 50 \text{ mA}) < 1.0B$; $I_R < 0.1 \text{ mKA}$; $C_D < 4.0 \text{ m}\Phi$; $t_{RR} < 6 \text{ Hz}$	SOT23,SOD23	A1-A2-K1,K2
ZB	FMMT4123	ZETEX	npn	$V_{CB0}=40B; I_C=200 \text{ mA}; P_0=330 \text{ mBT}; h_{21}=50150; f_T>250 \text{ MFu}$	SOT23,SOD23	B·E·C
ZC	FMMT4124	ZETEX	npn	V_{CB0} =30 B; I_C =200 mA; P_D =330 mBT; h_{21} =120360; f_T >300 M Γ_{IJ}	SOT23,SOD23	B·E·C
ZC	KST4124	SAMS	npn	$V_{CB0}=30B$; $I_{C}=200$ mA; $P_{D}=350$ mBT; $h_{21}=120360$; $f_{T}>300$ MF I_{L}	SOT23,SOD23	B·E·C
ZCA	KN3904S	KEC	npn	V _{CB0} =60 B; I _C =200 mA; P _D =350 mBT	SOT23,SOD23	B·E·C
ZD	FMMT4125	ZETEX	pnp	V_{CB0} = 30 B; I_C = 200 mA; P_D = 330 mBT; h_{21} =50150; f_T > 200 MF $_{II}$	SOT23,SOD23	B·E·C
ZD	KST4125	SAMS	pnp	V_{CB0} =30B; I_C =200 mA; P_D =350 mBT; h_{21} =50150; f_T >200 MFu	SOT23,SOD23	B·E·C
ZE	FMMT4126	ZETEX	pnp	V_{CB0} = 25 B; I_C = 200 mA; P_D = 330 mBT; h_{21} > 60; f_T > 250 MFu,	SOT23,SOD23	B·E·C
ZFD	BCV26	ZETEX	dpnp	V_{CB0} =40B; I_C =500 mA; P_D =330 mBt; h_{21} >100; f_T >200 M Γ U,	SOT23,SOD23	B·E·C
ZFE	BCV46	ZETEX	dpnp	V_{CB0} =80 B; I_C =500 mA; P_D =330 mBr; h_{21} >400; f_T >200 MFu	SOT23,SOD23	B·E·C
ZFF	BCV27	ZETEX	dnon	$V_{CR0}=40B; I_C=500 \text{ mA}; P_D=330 \text{ mBT}; h_{21}>100; f_T>170 \text{ MFL}$	SOT23,SOD23	B·E·C
ZFG	BCV47	ZETEX	dnpn	V _{CR0} =80 B; I _C =500 mA; P _D =330 mBr; h ₂₁ >400; f _T >170 MFu	SOT23.SOD23	
ZK-	2SJ451	REN	pMOS	V _{DS} =20B;I _D =200mA;P _D =150mBT;R _{DS(m)} <90m	SOT23 SOD23	G·S·D
ZM-	2SJ452	REN	pMOS	V _{DS} =50B; I _D =200mA; P _D =150mBT; R _{OSion} < 120m	SOT23.SOD23	G·S·D
70	2PC4081Q	PHIL	non	V _{CR0} =50B; I _C =100 MA; P _C =200 MBτ; h ₂₁ =120270; f ₇ >100 MΓц	SOT323.SC70	100000000000000000000000000000000000000
ZR	2PC4081R	PHIL	non	V _{CB0} =50 B; I _C =100 мА; P _D =200 мВт; h ₂₁ =180390; f _T >100 МГц	SOT323.SC70	
ZR	MSD1819ART1	MOT	non	V _{CB0} =60 B; I _C =100 mA; P _D =150 mBτ; h ₂₁ =210340	SOT323,SC70	
ZRA	KN3903S	KEC	non	V _{cnn} =60B; I _c =200 mA; P _n =350 mBt	SOT23.SOD23	
ZS	2PC4081S	PHIL	non	V _{CR0} =50B; I _C =100 mA; P _D =200 mBT; h ₂₁ =270560; f _T >100 MFu	SOT323.SC70	
ZS-	2SC5702	REN	non	V _{cen} =15B; I _c =50 MA; P _n =80 MB _T ; h ₂₁ =80160; f _T >6.5 ΓΓ _L		B·E·C
ZS1	ZHCS1000	ZETEX	shd	V _R <40 B; I _F <1 A; V _F (I _F =1 A)<0.425 B; I _B <100 мкA; C _D <25 пΦ; I _{BB} <12 нс	SOT23.SOD23	100000000000000000000000000000000000000
ZS5	ZHCS1000 ZHCS500	ZETEX	shd	V _R <40 B; I _E <0.5 A; V _E (I _E =0.5 A)<0.55 B; I _E <40 m; A; C _D <20 πΦ; t _{RR} <10 HC	SOT23,30D23	100,000,000
ZS7	ZHCS750	ZETEX	shd	V _R <40 B;I _F <0.75 A;V _F (I _F =0.75 A)<0.49 B;I _R <0.1 мкА;C _D <25 пФ; I _{RR} <12 нс	SOT23,SOD23	10.000
ZU-	2SJ486	REN	oMOS	V _{DS} =30B;I _D =300mA;P _D =150mBT;R _{DS(on)} <1.20m	SOT23.SOD23	G-S-D
ZZ1	CMPZDA4V7	CSI	dz×2	V _Z (I _{ZT} = 5 mA) = 4.45.0 B; I ₁ (V _R = 2.0 B) < 3.0 m; A; Z _{ZT} (I _{ZT} = 5 mA) < 800m; I _{ZM} = 38 mA	SOT23,SOD23	
772	CMPZDA5V1	CSI	dz×2	V _Z (I _{ZT} =5 MA)=4.85.4B;I _L (V _R =2.0 B)<2.0 mKA;Z _{ZT} (I _{ZT} =5 MA)<60 0 m; I _{ZM} =35 MA	SOT23,SOD23	K2•K1•A2,A1
ZZ3	CMPZDA5V6	CSI	dz×2	ZZ(Z; 5 MA) = 5.26.0 B; l({V _B = 2.0 B} < 1.0 MKA; Z _{ZT} (I _{ZT} = 5 MA) < 40 OM; l _{JM} = 32 MA	SOT23,SOD23	K2•K1•A2,A1
ZZ4	CMPZDA6V2	CSI	dz×2	Z ₂ (I _{ZT} 5 mA) = 5.86.6 B; I _L (V _R = 4.0 B) < 3.0 m; A; Z _{ZT} (I _{ZT} 5 mA) < 10 Om; I _{ZM} = 28 mA	SOT23,SOD23	K2•K1•A2,A1
ZZ 5	CMPZDA6V8	CSI	dz×2	V _Z (I _{ZT} =5 mA)=6.47.2 B;I _L (V _R =4.0 B)<2.0 mrA;Z _{ZT} (I _{ZT} =5 mA)<15 Om; I _{ZM} =25 mA	SOT23,SOD23	K2-K1-A2,A1
ZZ6	CMPZDA7V5	CSI	dz×2	V _Z (I _{ZT} =5mA)=7.07.9B;I _L (V _R =5.0B)<1.0mrA;Z _{ZT} (I _{ZT} =5mA)<150m; I _{ZM} =23mA	SOT23,SOD23	K2•K1•A2,A1
227	CMPZDA8V2	CSI	dz×2	$V_Z(I_{ZT} = 5 \text{ mA}) = 7.78.7 \text{ B}; I_L(V_R = 5.0 \text{ B}) < 0.7 \text{ m/A}; Z_{ZT}(I_{ZT} = 5 \text{ mA}) < 150 \text{ m}; I_{ZM} = 21 \text{ mA}$	SOT23,SOD23	K2•K1•A2,A1
ZZ8	CMPZDA9V1	CSI	dz×2	$V_Z(I_{ZT}=5 \text{ MA})=8.59.6 \text{ B}; I_L(V_R=6.0 \text{ B})<0.5 \text{ M}; KA; Z_{ZT}(I_{ZT}=5 \text{ MA})<15 \text{ OM}; I_{ZM}=18 \text{ MA}$	SOT23,SOD23	K2•K1•A2,A1
ZZ9	CMPZDA10V	CSI	dz×2	$V_Z(I_{ZT} = 5 \text{ MA}) = 9.410.6B$; $I_L(V_B = 7.0B) \le 0.2 \text{ m/s}$; $I_{ZT} = 1.0 \text{ M}$; $I_{ZM} = 1.0 \text{ M}$;	SOT23,SOD23	K2•K1•A2,A1
	2SA1666	REN	ono	V _{CEO} * 15B; I _C * 200 mA; P _D * 150 mBt; h ₂₁ * 20200; f _T * 100 MFц	SOT346.SC59	B·E·C





SOT223



SOT89



SOT89/223, TO252/263...

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4
21	Gali-21	MC	amp	InGaP; f _{8D} = 0 8 ГГц; GAIN = 14 дБ	SOT-89, SC-62	IN • GND • OUT, VD • GND
33	Gali-33	MC	amp	InGaP; f _{8D} = 04ГГц; GAIN = 19.дБ	SOT-89, SC-62	IN • GND • OUT, VD • GND
51	Gali-51	MC	amp	InGaP, f _{8D} = 04ГГц; GAIN = 18 дБ	SOT-89, SC-62	IN • GND • OUT, VD • GND
52	Gali-52	MC	amp	InGaP; f _{8D} =02ГГц; GAIN=23дБ	SOT-89, SC-62	IN • GND • OUT, VD • GND
55	Gali-55	МС	amp	InGaP, f _{8D} =04ГГц; GAIN=21дБ	SOT-89, SC-62	IN • GND • OUT, VD • GND
651	PZT651	ON	npn	V _{DB0} =80 B; I _C =2 A; P _D =0.8 Вт; h ₂₁ >40; f _T >75 МГц	SOT-223, TO-261AA	B•C•E•C
720	BF720	STM	npn	$V_{DB} = 300 \text{ B}; I_{C} = 100 \text{ mA}; P_{D} = 1.5 \text{ B}\tau; h_{21} > 50; f_{T} = 60 \text{ M}\Gamma \text{ L}$	SOT-223, TO-261AA	B•C•E•C
721	BF721	STM	pnp	V _{CB} = 300 B; I _C = 100 мА; P _D = 1.5 Вт; h ₂₁ > 50; f _T = 60 МГц	SOT-223, TO-261AA	B•C•E•C
_	BCX68	SIEM	npn	$V_{CB0} = 20 \text{ B; } I_C = 1 \text{ A; } P_D = 1 \text{ Br; } h_{21} = 85375; f_T > 100 \text{ MF}_{LL}$	SOT-89, SC-62	B•C•E•C
_	BCX69	SIEM	pnp	V _{DB0} = 20 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 85375; f _T > 100 MF _Q	SOT-89, SC-62	B•C•E•C
01	Gali-1	МС	amp	InGaP, f _{8D} = 0 8 ГГц; GAIN = 12 дБ	SOT-89, SC-62	IN • GND • OUT, VD • GND
02	Gali-2	MC	amp	InGaP, f _{8D} = 0 8 ГГц; GAIN = 16 дБ	SOT-89, SC-62	IN • GND • OUT, VD • GND
03	Gali-3	MC	amp	InGaP, f _{8D} =03ГГц; GAIN=22дБ	SOT-89, SC-62	IN • GND • OUT, VD • GND
04	Gali-4	MC	amp	InGaP; f _{eD} = 04ГГц; GAIN = 17.5 дБ	SOT-89, SC-62	IN • GND • OUT, VD • GND
05	Gali-4	MC	amp	InGaP, f _{8D} = 04ГГц; GAIN = 18 дБ	SOT-89, SC-62	IN • GND • OUT, VD • GND
06	Gali-6	MC	amp	InGaP, f _{8D} = 04ГГц; GAIN = 11 дБ	SOT-89, SC-62	IN • GND • OUT, VD • GND
OC	MC78LC30HT1	ON	reg	LDO; V _{IN} = 2.512 B; V _{OUT} = 3.0 B; I _{OUT} = 50 mA	SOT-89, SC-62	GND • VIN • VOUT • VIN
0D	MC78LC40HT1		reg	LDO; V _{IN} = 2.512 B; V _{OUT} = 4.0 B; I _{OUT} = 50 MA	SOT-89, SC-62	GND • VIN • VOUT • VIN
0E	MC78LC50HT1	ON	reg	LDO; V _{IN} = 2.512 B; V _{OUT} = 5.0 B; I _{OUT} = 50 MA	SOT-89, SC-62	GND • VIN • VOUT • VIN
10Y	BZV49C10	PHIL	dz	$V_Z(I_{ZT}=5.0 \text{ mA}) = 9.410.6 \text{B}; Z_{ZT}(I_{ZT}=5.0 \text{ mA}) < 20 \text{ Om};$ $I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
1117	LT1117CST	LT	reg	LDO; V _{IN} < 15B; V _{REF} = 1.25B; I _{DUT} = 800 mA	SOT-223, TO-261AA	ADJ/GND • OUT • IN • OUT
11172	LT1117CST- 2.85	LT	reg	LDO; V _{IN} < 15B; V _{OUT} = 2.85B; I _{OUT} = 800 MA	SOT-223, TO-261AA	ADJ/GND • OUT • IN • OUT
11173	LT1117CST- 3.3	LT	reg	LDO; V _{IN} < 15B; V _{OUT} = 3.3B; I _{OUT} = 800 MA	SOT-223, TO-261AA	ADJ/GND • OUT • IN • OUT



SOT89



SOT223





T0263 D2PAK

Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3•4
11175	LT1117CST-5	LT	reg	LDO; V _{IN} < 15 B; V _{OLIT} = 5B; I _{OLIT} = 800 MA		ADJ/GND •
	Er i i i i i i i i i i i i i i i i i i i		log	255, 1 _N 1 155, 1 ₀₀₁ 155, 1 ₀₀₁ 155 1111	001 220, 10 20111	OUT • IN •
111825	LT1118CST- 2.5	LT	reg	LDO; V _{IN} < 15 B; V _{OUT} = 2.5B; I _{OUT} = 800 MA	SOT-223, TO-261AA	OUT • GND • IN • GND
111828	LT1118CST- 2.85	LT	reg	LDO; V _{IN} < 15 B; V _{OUT} = 2.85 B; I _{OUT} = 800 mA	SOT-223, TO-261AA	OUT • GND • IN • GND
11185	LT1118CST-5	LT	reg	LDO; V _{IN} < 15 B; V _{OUT} = 5B; I _{OUT} = 800 mA	SOT-223, TO-261AA	OUT • GND • IN • GND
11Y	BZV49C11	PHIL	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 10.411.6 \text{ B}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 20 \text{ Om};$ $I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
12Y	BZV49C12	PHIL	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 11.412.7 \text{ B}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 250 \text{ m}; I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
13Y	BZV49C13	PHIL	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 12.414.1 \text{ B; } Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 30 \text{ Om; } I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
15Y	BZV49C15	PHIL	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 13.815.6 \text{ B}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 30 \text{ Om};$ $I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
16Y	BZV49C16	PHIL	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 15.317.1 \text{ B; } Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 40.0 \text{m;}$ $I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
18Y	BZV49C18	PHIL	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 16.819.1 \text{ B}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 450 \text{m}; I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
1A	SXT3904	SIEM	npn	$V_{CB0} = 40B$; $I_C = 200 \text{ mA}$; $P_D = 1BT$; $h_{21} = 100300$; $f_T > 300 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
1D	SXTA42	SIEM	npn	$V_{CB0} = 300B$; $I_C = 500 \text{ mA}$; $P_D = 1 \text{ BT}$; $h_{21} > 40$; $f_T > 50 \text{ M/F}$ L	SOT-89, SC-62	B•C•E•C
1E	SXTA43	SIEM	npn	$V_{CBD} = 200B$; $I_C = 500 \text{ mA}$; $P_D = 1 \text{ BT}$; $h_{21} > 40$; $f_T > 50 \text{ M/L}$	SOT-89, SC-62	B•C•E•C
1XP	2SB1599P	PAN	pnp	$V_{CBD} = 50B$; $I_C = 3A$; $P_D = 1BT$; $h_{21} = 50100$; $f_T = 150 M\Gamma_{IJ}$	SOT-89, SC-62	B•C•E•C
1XQ	2SB1599Q	PAN	pnp	$V_{CBD} = 50B$; $I_C = 3A$; $P_D = 1BT$; $h_{21} = 80160$; $f_T = 150 M\Gamma_{IJ}$	SOT-89, SC-62	B•C•E•C
1XR	2SB1599R	PAN	prip	V _{CR0} = 50B; I _C = 3A; P _D = 1BT; h ₂₁ = 100220; f _T = 150 MF _{II}	SOT-89, SC-62	B•C•E•C
1YQ	2SD2457Q	PAN	non	V _{CB0} = 50 B; I _C = 1.5 A; P _D = 1 Bт; h ₂₁ = 80160; f _T = 150 МГц	SOT-89, SC-62	B•C•E•C
1YR	2SD2457R	PAN	non	V _{CB0} = 50B; I _C = 1.5 A; P _D = 1 Br; h ₂₁ = 120220; f _T = 150 MFu	SOT-89, SC-62	B•C•E•C
1ZQ	2SA1890Q	PAN	pnp	V _{CB0} = 80B; I _C = 1A; P _D = 1Bт; h ₂₁ = 120240; f _T = 120 МГц	SOT-89, SC-62	B•C•E•C
1ZR	2SA1890R	PAN	pnp	V _{CB0} = 80B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 170340; f _T = 120 МГц	SOT-89, SC-62	B•C•E•C
20Y	BZV49C20	PHIL	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 18.821.2 \text{ B; } Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 55 \text{ Om; } I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
22Y	BZV49C22	PHIL	dz	$V_z(I_{ZT} = 5.0 \text{ mA}) = 20.823.3 \text{ B}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 55 \text{ Om};$ $I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
24Y	BZV49C24	PHIL	dz	$V_z(I_{ZT} = 5.0 \text{ mA}) = 22.825.6 \text{ B; } Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 70 \text{ Om; } I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
27Y	BZV49C27	PHIL	dz	$V_Z(I_{ZT} = 2.0 \text{ mA}) = 25.128.9 \text{ B; } Z_{ZT}(I_{ZT} = 2.0 \text{ mA}) < 80 \text{ Om; } I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
2A	SXT3906	SIEM	pnp	$V_{CB0} = 40B$; $I_C = 200 \text{ mA}$; $P_D = 1BT$; $h_{21} = 100300$; $f_T > 250 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
2AR	2SC5026R	PAN	npn	V _{CB0} = 80B; I _C = 1A; P _D = 1BT; h ₂₁ = 120240; f _T = 120 MFu	SOT-89, SC-62	B•C•E•C
2AS	2SC5026S	PAN	npn	V _{CB0} = 80B; I _C = 1A; P _D = 1Bт; h ₂₁ = 170340; f _T = 120 МГц	SOT-89, SC-62	B•C•E•C
2D	SXTA92	SIEM	pnp	$V_{CBD} = 300B$; $I_C = 500 \text{ mA}$; $P_D = 1 \text{ BT}$; $h_{21} > 25$; $f_T > 50 \text{ MF} \text{ L}$	SOT-89, SC-62	B•C•E•C
2E	SXTA93	SIEM	prip	$V_{CB0} = 200B$; $I_C = 500 \text{ mA}$; $P_D = 1 \text{ BT}$; $h_{21} > 25$; $f_T > 50 \text{ MF} \text{ L}$	SOT-89, SC-62	B•C•E•C
2ER	2SD2459R	PAN	npn	V _{CBD} = 150B; I _C = 1 A; P _D = 1 Bт; h ₂₁ = 120240; f _T = 90 МГц	SOT-89, SC-62	B.C.E.C
2ES	2SD2459S	PAN	npn	V _{CB0} = 150B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 170340; f _T = 90 MF _{II}	SOT-89, SC-62	B•C•E•C
2F	2SB1612	PAN	pnp	V _{CB0} = 10B; I _C = 2A; P _D = 1BT; h ₂₁ = 200800; f _T = 60 MF _H	SOT-89, SC-62	B•C•E•C
2F	SXT2907A	SIEM	pnp	$V_{CR0} = 60B$; $I_C = 600 \text{ mA}$; $P_D = 1BT$; $h_{21} = 100300$; $f_T > 200 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
21	2SD2474	PAN	npn	V _{CB0} = 10B; I _C = 2A; P _D = 1BT; h ₂₁ = 200800; f _T = 180 MF _{II}	SOT-89, SC-62	B•C•E•C
2P	SXT2222A	SIEM	non	$V_{CB0} = 75B$; $I_C = 600 \text{ mA}$; $P_D = 1BT$; $h_{21} = 100300$; $f_T > 300 \text{ MF}_{IJ}$	SOT-89, SC-62	B•C•E•C
2Y4	BZV49C2V4	PHIL	dz	V _Z (I _{ZT} = 5.0 mA) = 2.22.6B; Z _{ZT} (I _{ZT} = 5.0 mA) < 100 Om; I _{ZM} = 250 mA	SOT-89, SC-62	A•K•A•K
2Y7	BZV49C2V7	PHIL	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 2.52.9 \text{B}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 100 \text{ Cm};$ $I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
30Y	BZV49C30	PHIL	dz	$V_Z(I_{ZT}=2.0 \text{ mA}) = 28.032.0 \text{ B}; Z_{ZT}(I_{ZT}=2.0 \text{ mA}) < 80 \text{ Om}; I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K









Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3•4
33Y	BZV49C33	PHIL	dz	V _Z (I _{ZT} = 2.0 mA) = 31.035.0B; Z _{ZT} (I _{ZT} = 2.0 mA) < 80 Om; I _{ZM} = 250 mA	SOT-89, SC-62	A•K•A•K
36Y	BZV49C36	PHIL	dz	V _Z (I _{ZT} =2.0 mA)=34.038.0B; Z _{ZT} (I _{ZT} =2.0 mA)<900m; I _{ZM} =250 mA	SOT-89, SC-62	A•K•A•K
37518	MC33375ST- 1.8	ON	reg	LDO; V _{IN} = 2.513 B, V _{OUT} = 1.8 B, I _{OUT} = 300 mA	SOT-223, TO-261AA	IN • ON/OFF • OUT • GND
37525	MC33375ST- 2.5	ON	reg	LDO; V _{IN} = 2.513 B; V _{OUT} = 2.5 B; I _{OUT} = 300 mA	SOT-223, TO-261AA	IN • ON/OFF • OUT • GND
37530	MC33375ST- 3.0	ON	reg	LDO; V _{IN} = 2.513 B; V _{OUT} = 3.0 B; I _{OUT} = 300 mA	SOT-223, TO-261AA	IN • ON/OFF • OUT • GND
37533	MC33375ST- 3.3	ON	reg	LDO; V _{IN} = 2.513 B, V _{OUT} = 3.3 B, I _{OUT} = 300 mA	SOT-223, TO-261AA	IN • ON/OFF • OUT • GND
37550	MC33375ST- 5.0	ON	reg	LDO; V _{IN} = 2.513 B; V _{CUT} = 5.0 B; I _{CUT} = 300 mA	SOT-223, TO-261AA	IN • ON/OFF • OUT • GND
39Y	BZV49C39	PHIL	dz	$V_Z(I_{ZT}=2.0 \text{ mA})=37.041.0B; Z_{ZT}(I_{ZT}=2.0 \text{ mA})<130 \text{ Om}; I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
3C	MC78LC33HT1	ON	reg	LDO; V _{IN} = 2.512 B; V _{OUT} = 3.3 B; I _{OUT} = 50 mA	SOT-89, SC-62	GND • VIN • VOUT • VIN
3Y0	BZV49C3V0	PHIL	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 2.83.2 \text{B}, Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 95 \text{ Om};$ $I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
3Y3	BZV49C3V3	PHIL	dz	$V_Z(I_{ZT}=5.0 \text{ mA}) = 3.13.5 \text{B; } Z_{ZT}(I_{ZT}=5.0 \text{ mA}) < 95 \text{ Om; } I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
3Y6	BZV49C3V6	PHIL	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 3.43.8 \text{B; } Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 90 \text{ Om; } I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
3Y9	BZV49C3V9	PHIL	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 3.74.1 \text{ B}, Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 90 \text{ Om};$ $I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
43Y	BZV49C43	PHIL	dz	$V_Z(I_{ZT}=2.0 \text{ mA})=40.046.0 \text{ B}; Z_{ZT}(I_{ZT}=2.0 \text{ mA})<150 \text{ Om}; I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
47Y	BZV49C47	PHIL	dz	$V_Z(I_{ZT} = 2.0 \text{ mA}) = 44.050.0 \text{ B}; Z_{ZT}(I_{ZT} = 2.0 \text{ mA}) < 170 \text{ Om}; I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
4F	Gali-4F	MC	amp	InGaP; f ₈₀ = 0 4ГГц; GAIN = 15 дБ	SOT-89, SC-62	IN • GND • OUT, VD • GND
4Y3	BZV49C4V3	PHIL	dz	$V_Z(I_{ZT}=5.0 \text{ mA})=4.04.6 \text{B}; Z_{ZT}(I_{ZT}=5.0 \text{ mA})<90 \text{ Om}; I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
4Y7	BZV49C4V7	PHIL	dz	$V_Z(I_{ZT}=5.0 \text{ mA})=4.45.0 \text{ B}; Z_{ZT}(I_{ZT}=5.0 \text{ mA})<80 \text{ Cm}; I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
51Y	BZV49C51	PHIL	dz	$V_Z(I_{ZT} = 2.0 \text{ mA}) = 48.054.0 \text{ B}; Z_{ZT}(I_{ZT} = 2.0 \text{ mA}) < 180 \text{ Om}; I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
56Y	BZV49C56	PHIL	dz	$V_Z(I_{ZT} = 2.0 \text{ mA}) = 52.060.0 \text{ B}; Z_{ZT}(I_{ZT} = 2.0 \text{ mA}) < 200 \text{ Om}; I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
5F	Gali-5F	MC	атр	InGaP, f ₈₀ = 04ГГц; GAIN = 20дБ	SOT-89, SC-62	IN • GND • OUT, VD • GND
5Y1	BZV49C5V1	PHIL	dz	$V_Z(I_{ZT}=5.0 \text{ mA})=4.85.4 \text{B}, Z_{ZT}(I_{ZT}=5.0 \text{ mA})<60 \text{ Om};$ $I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
5Y6	BZV49C5V6	PHIL	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 5.26.0 \text{ B}, Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 40 \text{ Cm};$ $I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
62Y	BZV49C62	PHIL	dz	V _Z (I _{ZT} = 2.0 mA) = 58.066.0B; Z _{ZT} (I _{ZT} = 2.0 mA) < 215 Om; I _{ZM} = 250 mA	SOT-89, SC-62	A•K•A•K
68Y	BZV49C68	PHIL	dz	V _Z (I _{ZT} =2.0 mA)=64.072.0B; Z _{ZT} (I _{ZT} =2.0 mA)<240 Om; I _{ZM} =250 mA	SOT-89, SC-62	A•K•A•K
6A	KIA7019AF	KEC	vd	V _{BG} = 1.9 B; VCC (max) = 15B; P _D = 500 MB _T	SOT-89, SC-62	VCC • GND • OUT • GND
6B	KIA7021AF	KEC	vd	V _{RG} = 2.1 B; VCC (max) = 15B; P _D = 500 mBT	SOT-89, SC-62	VCC • GND • OUT • GND











Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4
6C	KIA7023AF	KEC	vd	$V_{RG} = 2.3 \text{ B; VCC (max)} = 15 \text{ B; } P_D = 500 \text{ mB} \text{T}$	SOT-89, SC-62	VCC • GND • OUT • GND
6D	KIA7025AF	KEC	vd	V _{RG} = 2.5 B; VCC (max) = 15 B; P _D = 500 MB _T	SOT-89, SC-62	VCC • GND • OUT • GND
6E	KIA7027AF	KEC	vd	$V_{RG} = 2.7 \text{ B; VCC (max)} = 15 \text{ B; } P_0 = 500 \text{ MB} \text{T}$	SOT-89, SC-62	VCC • GND • OUT • GND
6F	Gali-6F	MC	amp	InGaP, f ₈₀ = 04ГГu; GAIN = 12дБ	SOT-89, SC-62	IN • GND • OUT, VD • GND
6F	KIA7029AF	KEC	vd	V _{RG} = 2.9 B; VCC (max) = 15 B; P _D = 500 MBT	SOT-89, SC-62	VCC • GND • OUT • GND
6G	KIA7031AF	KEC	vd	V _{RG} = 3.1 B; VCC (max) = 15 B; P _D = 500 мВт	SOT-89, SC-62	VCC • GND • OUT • GND
6H	KIA7032AF	KEC	vd	V _{RG} = 3.2 B; VCC (max) = 15 B; P ₀ = 500 мВт	SOT-89, SC-62	VCC • GND • OUT • GND
6J	KIA7033AF	KEC	vd	V _{RG} = 3.3 B; VCC (max) = 15 B; P _D = 500 мВт	SOT-89, SC-62	VCC • GND • OUT • GND
6K	KIA7034AF	KEC	vd	V _{RG} = 3.4 B; VCC (max) = 15 B; P _D = 500 мВт	SOT-89, SC-62	VCC • GND • OUT • GND
6L	KIA7035AF	KEC	vd	V _{RG} = 3.5 B; VCC (max) = 15 B; P _D = 500 MBT	SOT-89, SC-62	VCC • GND • OUT • GND
6M	KIA7036AF	KEC	vd	V _{RG} = 3.6 B; VCC (max) = 15 B; P _D = 500 mB _T	SOT-89, SC-62	VCC • GND • OUT • GND
6N	KIA7039AF	KEC	vd	V _{RG} = 3.9 B; VCC (max) = 15 B; P ₀ = 500 мВт	SOT-89, SC-62	VCC • GND • OUT • GND
6P	KIA7042AF	KEC	vd	V _{RG} = 4.2 B; VCC (max) = 15 B; P _D = 500 мВт	SOT-89, SC-62	VCC • GND • OUT • GND
6R	KIA7045AF	KEC	vd	V _{RG} = 4.5 B; VCC (max) = 15 B; P _D = 500 MB _T	SOT-89, SC-62	VCC • GND • OUT • GND
6Y2	BZV49C6V2	PHIL	dz	$V_Z(I_{ZT}=5.0 \text{ mA})=5.86.6 \text{ B}; Z_{ZT}(I_{ZT}=5.0 \text{ mA})<100 \text{ m}; I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
6Y8	BZV49C6V8	PHIL	dz	$V_Z(I_{ZT}=5.0 \text{ mA})=6.47.2 \text{ B}; Z_{ZT}(I_{ZT}=5.0 \text{ mA}) < 150 \text{ m}; I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
75Y	BZV49C75	PHIL	dz	$V_Z(I_{ZT} = 2.0 \text{ mA}) = 70.079.0 \text{ B}; Z_{ZT}(I_{ZT} = 2.0 \text{ mA}) < 255 \text{ Om}; I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
7Y 5	BZV49C7V5	PHIL	dz	V _Z (I _{ZT} = 5.0 mA) = 7.07.9 B; Z _{ZT} (I _{ZT} = 5.0 mA) < 15 Om; I _{ZM} = 250 mA	SOT-89, SC-62	A•K•A•K
8A	NJM78L02A	NJR	reg	V _{IN} = 2.530 B; V _{CUT} = 2.6B; I _{CUT} = 100 mÅ	SOT-89, SC-62	OUT • GND • IN • GND
8B	NJM78L03A	NJR	reg	V _{IN} = 2.530 B; V _{CUT} = 3.0 B; I _{CUT} = 100 mA	SOT-89, SC-62	OUT • GND • IN • GND
8C	NJM78L05A	NJR	reg	V _{IN} = 2.530 B; V _{OUT} = 5.0 B; I _{OUT} = 100 mA	SOT-89, SC-62	OUT • GND • IN • GND
8E	NJM78L06A	NJR	reg	V _{IN} = 2.530 B; V _{OUT} = 6.0 B; I _{OUT} = 100 mA	SOT-89, SC-62	OUT • GND • IN • GND
8F	NJM78L07A	NJR	reg	V _{IN} = 2.530 B; V _{OUT} = 7.0 B; I _{OUT} = 100 mA	SOT-89, SC-62	OUT • GND • IN • GND
8G	NJM78L08A	NJR	reg	V _{IN} = 2.530 B; V _{OUT} = 8.0 B; I _{OUT} = 100 mA	SOT-89, SC-62	OUT • GND • IN • GND
8H	NJM78L09A	NJR	reg	V _{IN} = 2.530 B; V _{OUT} = 9.0 B; I _{OUT} = 100 mA	SOT-89, SC-62	OUT • GND •
8J	NJM78L10A	NJR	reg	V _{IN} = 2.535 B; V _{CUT} = 10.0 B; I _{OUT} = 100 MA	SOT-89, SC-62	OUT • GND • IN • GND
8K	NJM78L12A	NJR	reg	V _{IN} = 2.535 B; V _{CUT} = 12.0 B; I _{OUT} = 100 мA	SOT-89, SC-62	OUT • GND • IN • GND
8L	NJM78L15A	NJR	reg	V _{IN} = 2.535 B; V _{CUT} = 15.0 B; I _{OUT} = 100 mA	SOT-89, SC-62	OUT • GND • IN • GND
8M	NJM78L18A	NJR	reg	V _{IN} = 2.540 B; V _{CUT} = 18.0 B; I _{OUT} = 100 mA	SOT-89, SC-62	OUT • GND • IN • GND











Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4
9N	NJM78L20A	NJR	reg	V _{IN} =2.540 B; V _{OUT} =20.0B; I _{OUT} =100 mA	SOT-89, SC-62	OUT • GND • IN • GND
BP .	NJM78L24A	NJR	reg	V _{IN} =2.540 B; V _{OUT} =24.0B; I _{OUT} =100 мА	SOT-89, SC-62	OUT • GND • IN • GND
9Y2	BZV49C8V2	PHIL	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 7.78.7 \text{ B}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 15 \text{ Om}; I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
9Z	NJM78L62A	NJR	reg	V _{IN} =2.530 B; V _{OUT} =6.2 B; I _{OUT} =100 mA	SOT-89, SC-62	OUT • GND • IN • GND
9B	NJM79L03UA	NJR	reg	V _{IN} =-2.530 B; V _{OUT} =-3.0 B; I _{OUT} =100 mA	SOT-89, SC-62	GND • IN • OUT • IN
9C	NJM79L05UA	NJR	reg	V _{IN} =-2.530 B; V _{OUT} =-5.0 B; I _{OUT} =100 mA	SOT-89, SC-62	GND • IN • OUT • IN
9E	NJM79L06UA	NJR	reg	V _{IN} =-2.530 B; V _{OUT} =-5.0 B; I _{OUT} =100 mA	SOT-89, SC-62	GND • IN • OUT • IN
9G	NJM79L08UA	NJR	reg	V _{IN} =-2.530 B; V _{OUT} =-8.0 B; I _{OUT} =100 mA	SOT-89, SC-62	GND • IN • OUT • IN
9H	NJM79L09UA	NJR	reg	V _{IN} =-2.530 B; V _{OUT} =-8.0 B; I _{OUT} =100 mA	SOT-89, SC-62	GND • IN • OUT • IN
9K	NJM79L12UA	NJR	reg	V _{IN} =-2.535B; V _{OUT} =-12.0B; I _{OUT} =100 мA	SOT-89, SC-62	GND • IN • OUT • IN
9L	NJM79L15UA	NJR	reg	V _{IN} =-2.535B; V _{OUT} =-15.0B; I _{OUT} =100 мA	SOT-89, SC-62	GND • IN • OUT • IN
9M	NJM79L18UA	NJR	reg	V _{IN} =-2.540 B; V _{OUT} =-18.0B; I _{OUT} =100 MA	SOT-89, SC-62	GND • IN • OUT • IN
gp	NJM79L24UA	NJR	reg	V _{IN} =-2.540 B; V _{OUT} =-24.0B; I _{OUT} =100 MA	SOT-89, SC-62	GND • IN • OUT • IN
9Y1	BZV49C9V1	PHIL	dz	$V_Z(I_{ZT}=5.0 \text{ mA})=8.59.6B; Z_{ZT}(I_{ZT}=5.0 \text{ mA})<15 \text{ Om};$ $I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
A27	PXTA27	PHIL	npn	V _{DBD} =60 B; I _C =500 мА; P _D =1 Bт; h ₂₁ > 100; f _T > 125 МГц	SOT-89, SC-62	B•C•E•C
AA	BCX51	PHIL	pnp	V _{CB0} =45 B; I _C =1 A; P _D =1 Br; h ₂₁ =40250; f _T =50 МГц	SOT-89, SC-62	B•C•E•C
AA	BCX51	SIEM	pnp	V _{CB0} =45 B; I _C =1 A; P _D =1 Br; h ₂₁ =40250; f ₇ =125 MFu	SOT-89, SC-62	B•C•E•C
AB	BCX516	PHIL	pnp	V _{DBD} =45 B; I _C =1 A; P _D =1 Bτ; h ₂₁ =40100; f ₁ =125 MΓц	SOT-89, SC-62	B•C•E•C
AC	2SA1690	ROHM	pnp	V _{CB0} =400B; I _C =100 mA; P _D =2BT; h ₂₁ =56270	SOT-89, SC-62	B•C•E•C
AC	BCX51-10	PHIL	pnp	V _{CBO} =45 B; I _C =1 A; P _D =1 Br; h ₂₁ =63160; f _T =50 МГц	SOT-89, SC-62	B•C•E•C
AC	BCX51-10	SIEM	pnp	V _{CB0} =45 B; I _C =1 A; P _D =1 Br; h ₂₁ =63160; f _T =125 MF _U	SOT-89, SC-62	B•C•E•C
AD	BCX5116	PHIL	pnp	V _{CB0} =45 B; I _C =1 A; P _D =1 Bτ; h ₂₁ =100250; f ₁ =50 MΓu	SOT-89, SC-62	B•C•E•C
AD	BCX5116	SIEM	pnp	V _{CB0} =45 B; I _C =1 A; P _D =1 Br; h ₂₁ =100250; f _T =125 МГц	SOT-89, SC-62	B•C•E•C
AE	BCX52	PHIL	pnp	V _{CBO} = 60 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 40250; f _T = 50 МГц	SOT-89, SC-62	B•C•E•C
AE	BCX52	SIEM	pnp	V _{CB0} =60 B; I _C =1 A; P _D =1 Br; h ₂₁ =40250; f _T =125 MFu	SOT-89, SC-62	B•C•E•C
AEP	2SB1424	ROHM	pnp	$V_{CB0}=20B; I_C=3A; P_D=500 \text{ MBT}; h_{21}=82180; f_T>240 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
AEQ	2SB1424	ROHM	pnp	$V_{DB0} = 20 \text{ B}; I_C = 3 \text{ A}; P_D = 500 \text{ MBT}; h_{21} = 120270; f_T > 240 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
AER	2SB1424	ROHM	pnp	$V_{DB0} = 20 \text{ B}; I_C = 3 \text{ A}; P_D = 500 \text{ mBT}; h_{21} = 180390; f_T > 240 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
AF	2SA1575	SANYO	pnp	$V_{CB0} = 200 \text{B}; I_C = 100 \text{mA}; P_0 = 500 \text{mB} \tau; h_{21} = 40320; fT = 400 \text{MF} \text{ц}$	SOT-89, SC-62	B•C•E•C
AF	BCX5206	PHIL	pnp	V _{CB0} =60 B; I _C =1 A; h ₂₁ =40100; f _T =125MΓ _Ц	SOT-89, SC-62	B•C•E•C
AF	BCX526	SIEM	pnp	V _{CB0} =60 B; I _C =1 A; P _D =1 Br; h ₂₁ =40100; f _T =125 MΓ _U	SOT-89, SC-62	B•C•E•C
AG	BCX5210	PHIL	pnp	V _{CB0} =60 B; I _C =1 A; P _D =1 Br; h ₂₁ =63160; f _T =50 МГц	SOT-89, SC-62	B•C•E•C
AG	BCX5210	SIEM	pnp	V _{CBD} =60 B; I _C =1 A; P _D =1 Br; h ₂₁ =63160; f _T =125 МГц	SOT-89, SC-62	B•C•E•C
AGP	2SA1797	ROHM	pnp	$V_{CB0} = 50 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ MBT}; h_{21} = 82180; f_T > 200 \text{ MF} \text{ L}$	SOT-89, SC-62	B•C•E•C
AGQ	2SA1797	ROHM	pnp	V _{CB0} =50 B; I _C =2 A; P _D =500 мВт; h ₂₁ =120270; f _T >200 МГц	SOT-89, SC-62	B•C•E•C
AH	BCP53	ON	pnp	V _{CEO} =80B; I _C =1.5 A; P _D =1.5 Bт; h ₂₁ =40250; f _T =50 МГц	SOT-223, TO-261AA	E•C•B•C
AH	BCX53	PHIL	pnp	V _{DB0} = 100B; I _C = 1A; P _D = 1Bт; h ₂₁ = 40250; f ₁ = 50МГц	SOT-89. SC-62	B•C•E•C
AH	BCX53	SIEM	pnp	V _{CB0} = 80 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 40250; f _T = 125 MFu	SOT-89, SC-62	B•C•E•C
AH-10	BCP53-10	ON	pnp	V _{CEO} =80B; I _C =1.5A; P _D =1.5Bт; h ₂₁ =63160; f _T =50МГц	SOT-223, TO-261AA	
AH-16	BCP53-16	ON	pnp	V _{CEO} = 80 B; I _C = 1.5 A; P _D = 1.5 Bτ; h ₂₁ = 100250; f _T = 50 ΜΓц	SOT-223, TO-261AA	











Код	Типономинал	_				
	MITCHIOMORALINI	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4
AHN	2SA1759	ROHM	pnp	$V_{CB0} = 400 \text{ B}; I_C = 100 \text{ mA}; P_D = 500 \text{ mBT}; h_{21} = 56120; f_T > 12 \text{ MFu},$	SOT-89, SC-62	B•C•E•C
AHP	2SA1759	ROHM	pnp	$V_{C80} = 400 \text{ B}; I_C = 100 \text{ mA}; P_D = 500 \text{ mBT}; h_{21} = 82180; f_T > 12 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
AHQ	2SA1759	ROHM	pnp	$V_{CB0} = 400 \text{ B}; I_C = 100 \text{ mA}; P_D = 500 \text{ mBT}; h_{21} = 120270; f_T > 12 \text{ MFц}$	SOT-89, SC-62	B•C•E•C
AHQ	2SD2098	ROHM	npn	$V_{CB0} = 50B$; $I_C = 5A$; $P_D = 500 \text{ mBT}$; $h_{21} = 120270$; $f_T > 150 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
AHR	2SD2098	ROHM	npn	$V_{CB0} = 50B$; $I_C = 5A$; $P_D = 500 \text{ mBT}$; $h_{21} = 180390$; $f_T > 150 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
AHS	2SD2098	ROHM	npn	$V_{CB0} = 50B$; $I_C = 5A$; $P_D = 500 \text{ mBT}$; $h_{21} = 270560$; $f_T > 150 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
AJ	BCX536	PHIL	pnp	V _{CB0} = 100 B; I _C = 1 A; h ₂₁ = 40 100; f _T = 50 МГц	SOT-89, SC-62	B•C•E•C
AJ	BCX536	SIEM	pnp	$V_{CB0} = 80B$; $I_C = 1A$, $P_D = 1BT$; $h_{21} = 40100$; $f_T = 125 M\Gamma_U$	SOT-89, SC-62	B•C•E•C
AJN	2SA1812	ROHM	pnp	$V_{CBO} = 400 \text{ B}; I_C = 500 \text{ mA}; P_D = 500 \text{ mBT}; h_{21} = 56120; f_T > 12 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
AJP	2SA1812	ROHM	pnp	$V_{CB0} = 400 \text{ B}$; $I_C = 500 \text{ mA}$; $P_D = 500 \text{ mBT}$; $h_{21} = 82180$; $f_T > 12 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
AJQ	2SA1812	ROHM	pnp	$V_{CB0} = 400 B$, $I_C = 500 \text{ mA}$, $P_D = 500 \text{ mB}_T$; $h_{21} = 120270$; $f_T > 12 \text{ MF}_L$	SOT-89, SC-62	B•C•E•C
AK	BCX5310	PHIL	pnp	V _{CBD} = 100 B; I _C = 1 A; P _D = 1 Вт; h ₂₁ = 63160; f _T = 50 МГц	SOT-89, SC-62	B•C•E•C
AK	BCX5310	SIEM	pnp	V _{CB0} =80B; I _C =1A; P _D =1Bт; h ₂₁ =63160; f _T =125 МГц	SOT-89, SC-62	B•C•E•C
AL	BCX5316	PHIL	pnp	V _{CB0} = 100B; I _C = 1 A; P _D = 1 Bт; h ₂₁ = 100250; f _T = 50 МГц	SOT-89, SC-62	B•C•E•C
AL	BCX5316	SIEM	pnp	V _{CB0} =80B; I _C =1A; P _D =1Bτ; h ₂₁ =100250; f _T =125 MΓц	SOT-89, SC-62	B•C•E•C
ALP	2SA1900	ROHM	pnp	$V_{CR0} = 60B$; $I_C = 1A$; $P_D = 500 \text{ mB}_T$; $h_{21} = 82180$; $f_T > 150 \text{ MF}_U$	SOT-89, SC-62	B•C•E•C
ALQ	2SA1900	ROHM	pnp	$V_{CBD} = 60B$; $I_C = 1A$; $P_D = 500 \text{ mBT}$; $h_{21} = 120270$; $f_T > 150 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
ALR	2SA1900	ROHM	pnp	$V_{CR0} = 60B$; $I_C = 1A$; $P_D = 500 \text{ mBT}$; $h_{CT} = 180390$; $f_T > 150 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
AM	BCX5216	PHIL	pnp	V _{CR0} = 60 B; I _C = 1 A; P _D = 1 Вт; h ₂₁ = 100250; f _T = 50 МГц	SOT-89, SC-62	B•C•E•C
AM	BCX5216	SIEM	pnp	V _{CBD} = 60 B; I _C = 1 A; P _D = 1 Вт; h ₂₁ = 100250; f _T = 125 МГц	SOT-89, SC-62	B•C•E•C
AQ	2SB766Q	PAN	pnp	V _{CBD} =30B; I _C =1A; P _D =1BT; h ₂₁ =85170; f _T =200 MF _U	SOT-89, SC-62	B•C•E•C
AR	2SB766R	PAN	pnp	V _{CB0} = 30B; I _C = 1A; P _D = 1Bτ; h ₂₁ = 120240; f _T = 200 MΓц	SOT-89, SC-62	B•C•E•C
AR	2SC3338	REN	non	V _{cm} = 20B; I _c = 50 мА; P _D = 400 мВт; P _D = 8.3 дБ; f _T > 3.5 ГГц	SOT-89, SC-62	B•C•E•C
AR1	BSR40	PHIL	npn	V _{CR0} = 70B; I _C = 1 A; P _D = 1 Вт; h ₂₁ = 40120; f _T > 100 МГц	SOT-89, SC-62	B•C•E•C
AR2	BSR41	PHIL	non	V _{CB0} = 70B; I _C = 1A; P _D = 1BT; h ₂₁ = 100300; f _T > 100	SOT-89, SC-62	B•C•E•C
AR3	BSR42	PHIL	npn	V _{CBD} = 90 B; I _C = 1 A; P _D = 1 Bт; h ₂₁ = 40120; f _T > 100 МГц	SOT-89, SC-62	B•C•E•C
AR4	BSR43	PHIL	non	$V_{CB0} = 90B$; $I_C = 1A$; $P_D = 1BT$; $h_{21} = 100300$; $f_T > 100 M\Gamma_U$	SOT-89, SC-62	B•C•E•C
AS	2SB766S	PAN	prip	V _{CB0} = 30B; I _C = 1A; P _D = 1Bт; h ₂₁ = 170340; f _T = 200 МГц	SOT-89, SC-62	B•C•E•C
AS1	BST50	PHIL	dpnp	V _{CBD} =60B; I _C =500 MA; P _D =1BT; h ₂₁ >2000	SOT-89, SC-62	B•C•E•C
AS1	BST50	MOT	dpnp	V _{CR0} = 60B; I _C = 500 mA; P _D = 1BT; h ₂₁ > 2000	SOT-89, SC-62	B•C•E•C
AS1	BST50	ZETEX	dpnp	V _{CR0} =60B; I _C =500mA; P _D =1BT; h ₂₁ >2000	SOT-89, SC-62	B•C•E•C
AS2	BST51	PHIL	dpnp	V _{CR0} = 80 B; I _C = 500 mA; P _D = 1 BT; h ₂₁ > 2000	SOT-89, SC-62	B•C•E•C
AS2	BST51	MOT	dono	V _{CR0} = 80B; I _C = 500 mA; P _D = 1BT; h ₂₁ > 2000	SOT-89, SC-62	B•C•E•C
AS2	BST51	ZETEX	dpnp	V _{CB0} = 80B; I _C = 500 mA; P _D = 1 B _T ; h ₂₁ > 2000	SOT-89, SC-62	B•C•E•C
AS3	BSP52	ON	dnpn	$V_{CBD} = 90B$; $I_C = 800 \text{ mA}$; $P_D = 800 \text{ mB} \text{ T}$; $h_{21} > 2000$	SOT-223, TO-261AA	B•C•E•C
AS3	BST52	PHIL	dpnp	V _{CR1} =90B; I _C =500 MA; P _D =1BT; h ₂₁ >2000	SOT-89, SC-62	B•C•E•C
AS3	BST52	MOT	dpnp	V _{CR0} = 90B; I _C = 500 MA; P _D = 1BT; h ₂₁ > 2000	SOT-89, SC-62	B•C•E•C
AS3	BST52	ZETEX	dpnp	V _{CR0} = 90 B; I _C = 500 mA; P _D = 1 B _T ; h ₂₁ > 2000	SOT-89, SC-62	B•C•E•C
AT	2SD1470	REN	dnpn	V _{CB0} = 60B; I _C = 1A; P _D = 1Br; h ₂₁ = 2000100000	SOT-89, SC-62	B•C•E•C
AT1	BST39	PHIL	non	V _{CB0} =400B; I _C =1A; P _D =1Bτ; h ₂₁ >40; f _T >70 MΓц	SOT-89, SC-62	B•C•E•C
AT1	BST39	ZETEX	non	V _{CP0} =400B; I _C =1A; P _D =1BT; h ₂₁ >40; f _T >70MFu	SOT-89, SC-62	B•C•E•C
AT2	BST40	PHIL	non	V _{CB0} =300B; I _C =1A; P _D =1BT; h ₂₁ >40; f _T >70MFu	SOT-89, SC-62	B•C•E•C
AT2	BST40	ZETEX	non	V _{CR0} = 300 B; I _C = 1 A; P _D = 1 B _T , h ₂₁ > 40; f _T > 70 MFu	SOT-89, SC-62	B•C•E•C
ATN	2SA1812	ROHM	pnp	V _{D90} = 400 B; I _C = 500 мA; P _D = 500 мВт; h _{D1} = 56120; f _T > 12 МГц	SOT-89, SC-62	B•C•E•C
ATP	2SA1812	ROHM	prip	V _{CB0} = 400 B; I _C = 500 MA; P _D = 500 MBT; h _{Cl} = 82180; f _T > 12 MFu,	SOT-89, SC-62	B•C•E•C
ATQ	2SA1812	ROHM	pnp	V_{CB0} = 400B; I_C = 500 mA; P_D = 500 mBr; h_{21} = 120270; f_T > 12 M f_{11}	SOT-89, SC-62	B•C•E•C
BA	2SD1367A	REN	npn	V _{CB0} = 20B; I _C = 2A; P _D = 1Bт; h ₂₁ = 100200; f _T = 100 МГц	SOT-89, SC-62	B•C•E•C
BA	BCX54	PHIL	non	V _{CEO} = 45B; I _C = 1A; P _D = 1Br; h ₂₁ = 40250; f _T = 130 MF _U	SOT-89, SC-62	B•C•E•C
BA	BCX54	SIEM	non	V _{CB0} = 45B; I _C = 1A; P _D = 1BT; h ₂₁ = 40250; f _T = 100 MF _U	SOT-89, SC-62	B•C•E•C
BAP	2SB1132	ROHM	pnp	V _{CBD} =40B; I _C = 1 A; P _D =500 мВт; h ₂₁ =82180; f _T > 150 МГц	SOT-89, SC-62	B•C•E•C







SOT223



SOT89 SC62



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4
BAQ	2SB1132	ROHM	рпр	$V_{CB0} = 40 \text{ B}; I_C = 1 \text{ A}; P_D = 500 \text{ mBT}; h_{21} = 120270; f_T > 150 \text{ MFц}$	SOT-89, SC-62	B•C•E•C
BAR	2SB1132	ROHM	pnp	V_{CBD} = 40 B; I_C = 1 A; P_D = 500 MBT; h_{21} = 180390; f_T > 150 MF $_{II}$	SOT-89, SC-62	B•C•E•C
BB	2SD1367B	REN	npn	V _{CBD} =20 B; I _C =2 A; P _D =1 Br; h ₂₁ =160320; f _T =100 МГц	SOT-89, SC-62	B•C•E•C
BB	BCX546	PHIL	npn	V _{CB0} =45 B; I _C =1 A; P _D =1 Br; h ₂₁ =40100; f _T =100 МГц	SOT-89, SC-62	B•C•E•C
BB	BCX546	SIEM	npn	V _{CB0} =45 B; I _C =1 A; P _D =1 BT; h ₂₁ =40100; f _T =100 MFu	SOT-89, SC-62	B•C•E•C
BC	2SD1367C	REN	npn	V _{CB0} =20 B; I _C =2 A; P _D =1 Вт; h ₂₁ =250500; f _T =100 МГц	SOT-89, SC-62	B•C•E•C
BC	BCX5410	PHIL	npn	V _{CBD} =45 B; I _C =1 A; P _D =1 Br; h ₂₁ =63160; f _T =130 MΓu,	SOT-89, SC-62	B•C•E•C
BC	BCX5410	SIEM	npn	V _{CB0} =45 B; I _C =1 A; P _D =1 Br; h ₂₁ =63160; f _T =100 MΓu	SOT-89, SC-62	B•C•E•C
BCP	2SB1188	ROHM	pnp	$V_{CB0} = 40 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ mBT}; h_{21} = 82180; f_T > 100 \text{ MFц}$	SOT-89, SC-62	B•C•E•C
BCQ	2SB1188	ROHM	pnp	$V_{CB0} = 40 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ mBT}; h_{21} = 120270; f_T > 100 \text{ M}\Gamma_{IJ}$	SOT-89, SC-62	B•C•E•C
BCR	2SB1188	ROHM	pnp	$V_{CB0} = 40 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ mBT}; h_{21} = 180390; f_T > 100 \text{ MFц}$	SOT-89, SC-62	B • C • E • C
BD	BCX5416	PHIL	npn	V _{CB0} =45 B; I _C =1 A; P _D =1 Br; h ₂₁ =100250; f _T =130 МГц	SOT-89, SC-62	B•C•E•C
BD	BCX5416	SIEM	npn	V _{CB0} =45 B; I _C =1 A; P _D =1 Br; h ₂₁ =100250; f _T =100 МГц	SOT-89, SC-62	B•C•E•C
BDP	2SB1189	ROHM	pnp	V_{CB0} =80B; I_C =700 mA; P_D =500 mB1; h_{21} =82180; f_T >100 M Γ_{IJ}	SOT-89, SC-62	B•C•E•C
BDQ	2SB1189	ROHM	pnp	$V_{CB0} = 80 \text{ B}; I_C = 700 \text{ mA}; P_D = 500 \text{ mBT}; h_{21} = 120270; f_T > 100 \text{ MFц}$	SOT-89, SC-62	B•C•E•C
BDR	2SB1189	ROHM	pnp	V_{CB0} =80 B; I_C =700 mA; P_D =500 mBr; h_{21} =180390; f_T >100 M Γ_{IJ}	SOT-89, SC-62	B•C•E•C
BE	BCX55	PHIL	npn	V _{CB0} =60 B; I _C =1 A; P _D =1 Br; h ₂₁ =40250; f _T =130 MFu	SOT-89, SC-62	B•C•E•C
BE	BCX55	SIEM	npn	V _{CB0} =60 B; I _C =1 A; P _D =1 Br; h ₂₁ =40250; f _T =100 MFu	SOT-89, SC-62	B•C•E•C
BE_	2SB1260	ROHM	pnp	$V_{CB0} = 80 \text{ B}; I_C = 1 \text{ A}; P_D = 2 \text{ BT}; h_{21} = 82390; f_T > 100 \text{ MFц}$	SOT-89, SC-62	B•C•E•C
BF	BCX5506	SIEM	npn	V _{CB0} = 60 B; I _C = 1 A; P _D = 1 Вт; h ₂₁ = 40100; f _T = 100 МГц	SOT-89, SC-62	B•C•E•C
BF	BCX556	PHIL	npn	V _{CB0} =60 B; I _C =1 A; P _D =1 Br; h ₂₁ =40100; f _T =100 МГц	SOT-89, SC-62	B•C•E•C
BFP	2SB1308	ROHM	pnp	$V_{CB0} = 30 \text{ B}; I_C = 3 \text{ A}; P_D = 500 \text{ MBT}; h_{21} = 82180; f_T > 120 \text{ MFц}$	SOT-89, SC-62	B•C•E•C
BFQ	2SB1308	ROHM	pnp	$V_{CR0} = 30 \text{ B; } I_C = 3 \text{ A; } P_D = 500 \text{ MBT; } h_{21} = 120270; f_T > 120 \text{ MFц}$	SOT-89, SC-62	B•C•E•C
BFR	2SB1308	ROHM	pnp	$V_{CB0} = 30 \text{ B; } I_C = 3 \text{ A; } P_D = 500 \text{ MBT; } h_{21} = 180390; f_T > 120 \text{ MFц}$	SOT-89, SC-62	B•C•E•C
BG	BCX5510	PHIL	npn	V _{CBD} = 60 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 63160; f _T = 130 МГц	SOT-89, SC-62	B • C • E • C
BG	BCX5510	SIEM	npn	V _{CB0} = 60 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 63160; f _T = 100 МГц	SOT-89, SC-62	B•C•E•C
BGR	2SB1124R	SANYO	pnp	$V_{CB0} = 60 \text{ B}; I_C = 3 \text{ A}; P_D = 500 \text{ mBT}; h_{21} = 100200; f_T = 150 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
BGS	2SB1124S	SANYO	pnp	$V_{CB0} = 60 \text{ B}; I_C = 3 \text{ A}; P_D = 500 \text{ MBT}; h_{21} = 140280; f_T = 150 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
BGT	2SB1124T	SANYO	pnp	$V_{CB0} = 60 \text{ B}; I_C = 3 \text{ A}; P_D = 500 \text{ MBT}; h_{21} = 200400; f_T = 150 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
BGU	2SB1124U	SANYO	pnp	$V_{CBD} = 60 \text{ B; } I_C = 3 \text{ A; } P_D = 500 \text{ MBT; } h_{21} = 280560; f_T = 150 \text{ MFu}$	SOT-89, SC-62	B • C • E • C
ВН	2SB1001BH	REN	pnp	V _{CBD} =20 B; I _C =2 A; P _D =1 Br; h ₂₁ =100200; fT=150 МГц	SOT-89, SC-62	B•C•E•C
ВН	2SB1125	SANYO	dpnp	$V_{CR0} = 80 \text{ B}; I_C = 700 \text{ mA}; P_D = 500 \text{ mBT}; h_{21} > 5000; f_T = 200 \text{ MF } \text{ J}$	SOT-89, SC-62	B•C•E•C
BH	BCP56	ON	npn	V _{CEO} = 80 B; I _C = 1 A; P _D = 1.5 B _T ; h ₂₁ = 40250; f _T = 130 MF _U	SOT-223, TO-261AA	E•C•B•C
BH	BCX56	PHIL	npn	V _{CB0} = 100B; I _C = 1A; P _D = 1Bτ; h ₂₁ = 40250; f ₁ = 130 ΜΓ _Ц	SOT-89, SC-62	B•C•E•C
ВН	BCX56	SIEM	npn	V _{CB0} =80 B; I _C =1 A; P _D =1 Br; h ₂₁ =40250; f ₁ =100 MΓ _U	SOT-89, SC-62	B•C•E•C
BH-10	BCP56-10	ON	npn	V _{CE0} =80B; I _C =1A; P _D =1.5Br; h ₂₁ =63160; f _T =130 MFu	SOT-223, TO-261AA	E•C•B•C
BH-16	BCP56-16	ON	npn	V _{CEO} = 80B; I _C = 1A; P _D = 1.5 BT; h ₂₁ = 100250; f _T = 130 MFu,	SOT-223, TO-261AA	E•C•B•C
BHP	2SB1386	ROHM	pnp	V _{DBD} =30 B; I _C =5 A; P _D =500 мВт; h ₂₁ =82180; f _T >120 МГц	SOT-89, SC-62	B•C•E•C
BHQ	2SB1386	ROHM	pnp	V _{DBD} = 30 B; I _C = 5 A; P _D = 500 мВт; h ₂₁ = 120270; f _T > 120 МГц	SOT-89, SC-62	B•C•E•C
BHR	2SB1386	ROHM	pnp	V _{CBD} =30 B; I _C =5 A; P _D =500 мВт; h ₂₁ =180390; f _T > 120 МГц.	SOT-89, SC-62	B•C•E•C
BI	2SB1126	SANYO		V _{CB0} =80 B; I _C =1.5 A; P _D =500 мВт; h ₂₁ >4000; f _T =120 МГц	SOT-89, SC-62	B•C•E•C
BJ	2SB1001BJ	REN	pnp	V _{DB0} = 20 B; I _C = 2 A; P _D = 1 Вг; h ₂₁ = 160320; f ₁ = 150 МГц	SOT-89, SC-62	B•C•E•C
BJ	BCX5606	SIEM	npn	V _{CBD} = 80 B; I _C = 1 A; P _D = 1 Вг; h ₂₁ = 40100; f ₁ = 100 МГц	SOT-89, SC-62	B•C•E•C
BJ	BCX566	PHIL	npn	V _{DBD} = 80 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 40100; f ₁ = 50 МГц	SOT-89, SC-62	B•C•E•C
BJE	2SB1427	ROHM	pnp	V _{CB0} =20 B; I _C =2 A; P _D =500 MBT; h ₂₁ =390820; f _T >90 MFц	SOT-89, SC-62	B•C•E•C
BJS	2SB1427	ROHM	pnp	V _{CB0} =20 B; I _C =2 A; P _D =500 мBτ; h ₂₁ =270560; f _T >90 MΓц	SOT-89, SC-62	B•C•E•C
BJU	2SB1427	ROHM	pnp	V _{DB0} = 20 B; I _C = 2 A; P _D = 500 мВт; h ₂₁ = 5601200; f _T > 90 МГц	SOT-89, SC-62	B•C•E•C
				200	10000 2004 2000 2000	10 000000 100
BK	BCX5610	PHIL	npn	$V_{CB0} = 100B$; $I_C = 1A$; $P_D = 1BT$; $h_{21} = 63160$; $f_T = 130M\Gamma_U$	SOT-89, SC-62	B • C • E • C









SOT89 SOT223 TO252 TO2613 DPAK TO263 D2PAK

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4
BL	BCX5616	PHIL	npn	V _{CB0} = 100B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 100250; f _T = 130 MF ₄	SOT-89, SC-62	B•C•E•C
BL	BCX5616	SIEM	npn	$V_{CBD} = 80B$; $I_C = 1A$; $P_D = 1B\tau$; $h_{21} = 100250$; $f_T = 100 M\Gamma U$	SOT-89, SC-62	B•C•E•C
BLP	2SB1561	ROHM	pnp	$V_{CBD} = 60B$; $I_C = 2A$; $P_D = 500 \text{ MBT}$; $h_{21} = 82180$; $f_T > 200 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
BLQ	2SB1561	ROHM	pnp	$V_{CB0} = 60B$; $I_C = 2A$; $P_D = 500 \text{ MBT}$; $h_{21} = 120270$; $f_T > 200 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
BM	BCX5516	PHIL	npn	V _{CB0} = 60B; I _C = 1A; P _D = 1BT; h ₂₁ = 100250; f _T = 130 MF _U	SOT-89, SC-62	B•C•E•C
BM	BCX5516	SIEM	npn	V _{CBD} = 60 B; I _C = 1 A; P _D = 1 Bτ; h ₂₁ = 100250; f _T = 100 MΓ _{II}	SOT-89, SC-62	B•C•E•C
BO	2SA1200	TOSH	pnp	V_{CED} = 150 B; I_C = 50 mA; P_D = 500 mBT; h_{21} > 70140; f_T > 120 MFu	SOT-89, SC-62	B•C•E•C
BO	KTA1660	KEC	pnp	V_{CB0} = 150B; I_C = 50 mA; P_D = 500 mBT; h_{21} = 70140; f_T > 120 MF $_{LL}$	SOT-89, SC-62	B•C•E•C
BQ	2SB766AQ	PAN	pnp	$V_{CB0} = 60 \text{ B}; I_C = 1 \text{ A}; P_D = 1 \text{ Br}; h_{21} = 85170; f_T = 200 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
BR	2SB766AR	PAN	pnp	$V_{CB0} = 60B$; $I_C = 1A$; $P_D = 1B_T$; $h_{21} = 120240$; $f_T = 200 MFu$	SOT-89, SC-62	B•C•E•C
BR1	BSR30	PHIL	pnp	$V_{CB0} = 70 \text{ B}; I_C = 1 \text{ A}; P_D = 1 \text{ B}_T; h_{21} = 40120; f_T > 100 \text{ M}\Gamma_U$	SOT-89, SC-62	B•C•E•C
BR2	BSR31	PHIL	pnp	$V_{CB0} = 70B$; $I_C = 1A$; $P_D = 1Br$; $h_{21} = 100300$; $f_T > 100 M\Gamma_U$	SOT-89, SC-62	B•C•E•C
BR3	BSR32	PHIL	pnp	$V_{CB0} = 90B$; $I_C = 1A$; $P_D = 1BT$; $h_{21} = 40120$; $f_T > 100 M\Gamma_U$	SOT-89, SC-62	B•C•E•C
BR4	BSR33	PHIL	pnp	$V_{CB0} = 90B$; $I_C = 1A$; $P_D = 1BT$; $h_{21} = 100300$; $f_T > 100 M\Gamma_{IJ}$	SOT-89, SC-62	B•C•E•C
BS	2SB766AS	PAN	pnp	V _{CBD} = 60B; I _C = 1A; P _D = 1Bт; h ₂₁ = 170340; f _T = 200 МГц	SOT-89, SC-62	B•C•E•C
BS1	BST60	PHIL	dpnp	V _{CRD} = 60B; I _C = 500 mA; P _D = 1BT; h ₂₁ > 2000	SOT-89, SC-62	B•C•E•C
BS1	BST60	MOT	dpnp	V _{CPD} = 60B; I _C = 500 mA; P _D = 1BT; h ₂₁ > 2000	SOT-89, SC-62	B•C•E•C
BS1	BST60	ZETEX	dpnp	V _{CR0} = 60B; I _C = 500 mA; P _D = 1BT; h ₂₁ > 2000	SOT-89, SC-62	B•C•E•C
BS2	BST61	PHIL	dpnp	V _{CR0} =80B; I _C =500mA; P _D =1BT; h ₂₁ >2000	SOT-89, SC-62	B•C•E•C
BS2	BST61	MOT	dpnp	V _{CBD} = 80B; I _C = 500 mA; P _D = 1BT; h ₂₁ > 2000	SOT-89, SC-62	B•C•E•C
BS2	BST61	ZETEX	dpnp	V _{CRD} = 80B; I _C = 500 MA; P _D = 1BT; h ₂₁ > 2000	SOT-89, SC-62	B•C•E•C
BS3	BSP62	ON	dpnp	V _{CR0} = 90 B; I _C = 1 A; P _D = 1.25 Bτ; h ₂₁ > 2000; f _T = 200 ΜΓц	SOT-89, SC-62	B•C•E•C
BS3	BST62	PHIL	dpnp	V _{CB0} =90B; I _C =500mA; P _D =1BT; h ₂₁ >2000	SOT-89, SC-62	B•C•E•C
BS3	BST62	MOT	20.00	V _{CB0} =90B; I _C =500MA; P _D =1BT; h ₂₁ >2000	SOT-89, SC-62	B•C•E•C
BS3	BST62	ZETEX	dpnp	V _{CB0} =90B; I _C =500MA; P _D =1B1; II ₂₁ >2000 V _{CB0} =90B; I _C =500MA; P _D =1B1; II ₂₁ >2000	SOT-89, SC-62	B•C•E•C
BT	2SB1048	REN	dpnp	000 1 0 1 2 1 21	SOT-89, SC-62	B•C•E•C
		PHIL	dpnp	V _{CB0} = 60 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 2000100000		
BT1 BT2	BST15 BSP16	ON	pnp	V _{CB0} = 200B; I _C = 1 A; P _D = 1 BT; h ₂₁ = 30150; f _T > 15 MΓц	SOT-89, SC-62	B•C•E•C
2000			pnp	$V_{CB0} = 350B; I_C = 200 \text{ mA}; P_D = 1.28 \text{ BT}; h_{21} > 30; f_T > 15 \text{ MFu}$	SOT-223, TO-261AA	
BT2 BY	BST16 2SA1200	PHIL	prp	V_{C60} =350B; I_C =1A; P_D =1BT; h_{21} =30120; f_T >15M Γ_{IL} V_{C60} =150B; I_C =50mA; P_D =500mBT; h_{21} >120240; f_T >120M Γ_{IL}	SOT-89, SC-62 SOT-89, SC-62	B•C•E•C
BY	KTA1660	KEC	pnp	$V_{CB0} = 150 \text{ B; } I_C = 50 \text{ mA; } P_D = 500 \text{ mBr; } h_{21} = 120240; $ $f_T > 120 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
BYR210	PBYR2100CT	PHIL	shd x2	$V_R < 100 \text{ B}; V_F (I_F = 1 \text{ A}) < 0.69 \text{ B}; C_T < 100 \text{ n}\Phi$	SOT-223, TO-261AA	A1 • K1, K2 • A2 • K1, K2
BYR215	PBYR2150CT	PHIL	shd x2	$V_R < 150 \text{ B}; V_F (I_F = 1 \text{ A}) < 0.69 \text{ B}; C_T < 100 \text{ n}\Phi$	SOT-223, TO-261AA	A1 • K1, K2 • A2 • K1, K2
BYR220	PBYR220CT	PHIL	shd x2	$V_R \le 20 \text{ B}; V_F (I_F = 2 \text{ A}) \le 0.51 \text{ B}; C_T = 160 \text{ n}\Phi$	SOT-223, TO-261AA	A1 • K1, K2 • A2 • K1, K2
BYR225	PBYR225CT	PHIL	shd x2	$V_R < 25 \text{ B}; V_F (I_F = 2 \text{ A}) < 0.51 \text{ B}; C_T = 160 \text{ n}\Phi$	SOT-223, TO-261AA	A2 • K1, K2
BYR240	PBYR240CT	PHIL	shd x2	$V_R < 40 \text{ B}; V_F (I_F = 2 \text{ A}) < 0.7 \text{ B}; C_T = 60 \text{ n}\Phi$	SOT-223, TO-261AA	A2 • K1, K2
BYR245	PBYR245CT	PHIL	shd x2	$V_R < 45 \text{ B}; V_F (I_F = 2 \text{ A}) < 0.7 \text{ B}; C_T = 60 \text{ n}\Phi$	SOT-223, TO-261AA	A2 • K1, K2
BYR28	PBYR280CT	PHIL	shd x2	V _R <80 B; V _F (I _F =1 A)<0.69 B; C _T <100 nΦ	SOT-223, TO-261AA	A2 • K1, K2
BYR29	PBYR290CT	PHIL	shd x2	V _R <90 B; V _F (I _F =1 A)<0.69 B; C _T <100 nΦ	SOT-223, TO-261AA	A2 • K1, K2
CA	BCP68	MOT	npn	$V_{CEO} = 20B$; $I_C = 1A$; $P_D = 1.5BT$; $h_{21} = 85375$; $f_T = 60 MFu$	SOT-223, TO-261AA	
CAC	BC868	PHIL	npn	$V_{CB0} = 25 B$; $I_C = 1 A$; $P_D = 1 B\tau$; $h_{21} = 85375$; $f_T > 40 M\Gamma_H$	SOT-89, SC-62	B•C•E•C
CB	2SD1368	REN	npn	$V_{CB0} = 100B$; $I_C = 1 A$; $P_D = 1 B\tau$; $h_{21} = 160320$; $f_T = 100 M\Gamma \mu$	SOT-89, SC-62	B•C•E•C
CB	BCX6810	SIEM	npn	$V_{CB0} = 20B$; $I_C = 1A$; $P_D = 1BT$; $h_{21} = 85160$; $f_T = 100 M\Gamma_{II}$	SOT-89, SC-62	B•C•E•C





SOT223



SOT89



Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3•4
CBC	BC86810	PHIL	npn	$V_{CB0} = 25 \text{ B; } I_C = 1 \text{ A; } P_D = 1 \text{ Br; } h_{21} = 160500; f_T > 40 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
CBN	2SC4132	ROHM	npn	$V_{C80} = 120B$; $I_C = 2A$; $P_D = 500 \text{ mB} \text{ T}$; $h_{21} = 56120$; $f_T > 80 \text{ M} \Gamma \text{ U}$	SOT-89, SC-62	B•C•E•C
CBP	2SC4132	ROHM	npn	$V_{CBD} = 120B$; $I_C = 2A$; $P_D = 500 \text{ mB}\text{T}$; $h_{21} = 82180$; $f_T > 80 \text{ MF}\text{L}$	SOT-89, SC-62	B•C•E•C
CBQ	2SC4132	ROHM	npn	$V_{CB0} = 120B$; $I_C = 2A$; $P_D = 500 \text{ mBT}$; $h_{21} = 120270$; $f_T > 80 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
CBR	2SC4132	ROHM	npn	$V_{CB0} = 120B$; $I_C = 2A$; $P_D = 500 \text{ MBT}$; $h_{21} = 180390$; $f_T > 80 \text{MFu}$	SOT-89, SC-62	B•C•E•C
CC	2SD1368	REN	npn	$V_{CB0} = 100B$; $I_C = 1A$; $P_D = 1B_T$; $h_{21} = 250500$; $f_T = 100 M\Gamma U$	SOT-89, SC-62	B.C.E.C
CC	BCX6816	SIEM	npn	V _{DB0} = 20 B; I _C = 1 A; P _D = 1 Bτ; h ₂₁ = 100250; f _T = 100 MΓ _Ц	SOT-89, SC-62	B • C • E • C
CCC	BC86816	PHIL	npn	V _{CBD} = 25 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 100250; f _T > 40 MF _U	SOT-89, SC-62	B•C•E•C
CD	BCX6825	SIEM	npn	V _{CB0} =20 B; I _C =1 A; P _D =1 Br; h ₂₁ =160375; f _T =100 MΓ _U	SOT-89, SC-62	B•C•E•C
CDC	BC86825	PHIL	npn	V _{CB0} = 25 B; I _C = 1 A; P _D = 1 Вт; h ₂₁ > 160; f _T > 40 МГц	SOT-89, SC-62	B•C•E•C
CE	BCP69	MOT	pnp	V _{CE0} = 20B; I _C = 1A; P _D = 1.5 Bт; h ₂₁ = 85375; f _T = 60МГц	SOT-223, TO-261AA	E • C • B • C
CEC	BC869	PHIL	pnp	V _{CBD} = 25 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 85375; f ₁ > 40 МГц	SOT-89, SC-62	B•C•E•C
CEN	2SC4505	ROHM	npn	V _{CR0} = 400 B; I _C = 100 mA; P _D = 500 mBr; h ₂₁ = 56120; f _T > 20 MFu,	SOT-89, SC-62	B•C•E•C
CEP	2SC4505	ROHM	npn	V _{CRD} = 400 B; I _C = 100 mA; P _D = 500 mBT; h ₂₁ = 82180; f _T > 20 MFu,	SOT-89, SC-62	B•C•E•C
CEQ	2SC4505	ROHM	npn	V_{CB0} = 400B; I_C = 100 mA; P_D = 500 mBT; h_{21} = 120270; f_T > 20MF $_U$	SOT-89, SC-62	B•C•E•C
CF	BCX6910	SIEM	pnp	V _{CBD} = 20 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 85160; f _T = 100 МГц	SOT-89, SC-62	B•C•E•C
CFC	BC86910	PHIL	pnp	V _{CBD} = 25 B; I _C = 1 A; P _D = 1 Br; h ₂₁ > 160; f ₁ > 40 MF ₄	SOT-89, SC-62	B•C•E•C
CFQ	2SD2150	ROHM	npn	V _{CR0} = 40 B; I _C = 3 A; P _D = 500 мВт; h ₂₁ = 120270; f _T > 290 МГц	SOT-89, SC-62	B•C•E•C
CFR	2SD2150	ROHM	npn	$V_{CB0} = 40 \text{ B}; I_C = 3 \text{ A}; P_D = 500 \text{ mBT}; h_{21} = 180390; f_T > 290 \text{ MFц}$	SOT-89, SC-62	B•C•E•C
CFS	2SD2150	ROHM	npn	$V_{CB0} = 40 \text{ B}; I_C = 3 \text{ A}; P_D = 500 \text{ MBT}; h_{21} = 270560; f_T > 290 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
CG	BCX6916	SIEM	pnp	V _{CBD} = 20 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 100250; f _T = 100 MΓ ₄	SOT-89, SC-62	B•C•E•C
CGC	BC86916	PHIL	pnp	V _{CBD} = 25 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 100250; f _T > 40 MF _L	SOT-89, SC-62	B•C•E•C
CGP	2SC5053	ROHM	npn	V _{CR0} =60 B; I _C =1 A; P _D =500 мВт; h ₂₁ =82180; f _T >150 МГц	SOT-89, SC-62	B•C•E•C
CGQ	2SC5053	ROHM	npn	V _{CBO} =60 B; I _C =1 A; P _D =500 мВт; h ₂₁ =120270; f _T >150 МГц	SOT-89, SC-62	B•C•E•C
CGR	2SC5053	ROHM	npn	V _{CRD} = 60 B; I _C = 1 A; P _D = 500 мВт; h ₂₁ = 180390; f _T > 150 МГц	SOT-89, SC-62	B•C•E•C
CH	2SB1002CH	REN	pnp	V _{CBO} = 70 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 100200; fT = 150 МГц	SOT-89, SC-62	B•C•E•C
CH	BCX6925	SIEM	pnp	V _{CBO} = 20 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 160375; f _T = 100 MΓ _U	SOT-89, SC-62	B•C•E•C
CHC	BC86925	PHIL	pnp	V _{CBD} = 25 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 160; f _T > 40 MFu.	SOT-89, SC-62	B•C•E•C
CI	2SC4080	SANYO		V _{CB0} =200B; I _C =100 мA; P _D =500 мBτ; h ₂₁ =40320; f _T =400MΓμ	SOT-89, SC-62	B•C•E•C
CJ	2SB1002CJ	REN	pnp	V _{CBD} = 70 B; I _C = 1 A; P _D = 1 Br; h ₂₁ = 160320; fT = 150 MΓ _U	SOT-89, SC-62	B•C•E•C
CR	2SC4422	REN	npn	V _{CR0} =15B; I _C =50 мА; P _D =400 мВт; h ₂₁ =50250; f _T >4.5 ГГц	SOT-89, SC-62	B•C•E•C
CT	2SD1472	REN	dnon	V _{DB0} = 120B; I _C = 1.5 A; P _D = 1 Br; h ₂₁ = 200030000	SOT-89, SC-62	B•C•E•C
DA	2SD1418	REN	npn	V _{CRO} = 120B; I _C = 1A; P _D = 1Bτ; h ₂₁ = 60120; f _T = 140MΓц	SOT-89, SC-62	B•C•E•C
DA	BF622	PHIL	non	V _{CBD} =250B; I _C =50 мА; P _D =1Bт; h _{P1} >50; f _T >60 МГц	SOT-89, SC-62	B•C•E•C
DA	BF622	SIEM	npn	V _{CRD} = 250 B; I _C = 50 MA; P _D = 1 Bτ; h ₂₁ > 50; f _T = 100 MΓ _U	SOT-89, SC-62	B•C•E•C
DAP	2SD1664	ROHM	npn	V _{CB0} = 40 B; I _C = 1 A; P _D = 500 мВт; h ₂₁ = 82180; f _T > 150 МГц	SOT-89, SC-62	B•C•E•C
DAO	2SD1664	ROHM	npn	V _{CR0} =40 B; I _C =1 A; P _D =500 мВт; h ₂₁ =120270; f _T >150 МГц	SOT-89, SC-62	B•C•E•C
DAR	2SD1664	ROHM	npn	V _{DBD} = 40 B; I _C = 1 A; P _D = 500 мВт; h ₂₁ = 180390; f _T > 150 МГц	SOT-89, SC-62	B•C•E•C
DB	2SD1418	REN	npn	V _{CBD} = 120B; I _C = 1A; P _D = 1Bт; h ₂₁ = 100200; f _T = 140 МГц	SOT-89, SC-62	B•C•E•C
DB	BF623	PHIL	pnp	V _{CBD} =250B; I _C =50 MA; P _D =1BT; h ₂₁ >50; f _T >60 MΓц	SOT-89, SC-62	B•C•E•C
DB	BF623	SIEM	prip	V _{CB0} =250B; I _C =30 MA; P _D =1Bt; I ₂₁ >30; I ₇ =30 MFu; V _{CB0} =250B; I _C =50 MA; P _D =1Bt; I ₂₁ >50; I ₇ =100 MFu;	SOT-89, SC-62	B•C•E•C
DBP	2SD1766	ROHM		V _{CBD} =40 B; I _C =2A; P _D =500 mBτ; h ₂₁ =82180; f _T >100 MΓц	SOT-89, SC-62	B•C•E•C
DBQ	2SD1766	ROHM	npn		SOT-89, SC-62	B•C•E•C
DBR	2SD1766	ROHM	npn	V _{CB0} =40 B; I _C =2A; P _D =500 MBT; h ₂₁ =120270; f _T >100 MF _U	SOT-89, SC-62	B•C•E•C
DC		-	npn	V _{CB0} =40 B; I _C =2A; P _D =500 mBr; h ₂₁ =180390; f _T >100 mFq		
2770-2	2SD1418	REN	npn	V _{CB0} = 120B; I _C = 1A; P _D = 1BT; h ₂₁ = 160320; f _T = 140 MF _U	SOT-89, SC-62	B•C•E•C
DC	BF620	PHIL	npn	V _{CB0} =300B; I _C =50 MA; P _D =1 BT; h ₂₁ >50; f _T >60 MΓι ₄	SOT-89, SC-62	B•C•E•C
DC	BF720T1	ON	npn	V _{CB} = 300 B; I _C = 100 mA; P _D = 1.5 BT; h ₂₁ > 50; f _T = 60 MFu	SOT-223, TO-261AA	
DC	BFN20	SIEM	npn	V _{CBO} = 300 B; I _C = 50 μA; P _D = 1 Bτ; h ₂₁ > 40; f _T = 100 ΜΓ _U	SOT-89, SC-62	B•C•E•C
DCP	2SD1767	ROHM	npn	$V_{CB0} = 80 \text{ B}; I_C = 700 \text{ mA}; P_D = 500 \text{ mBT}; h_{E1} = 82180; f_T > 120 \text{ MFu}$	SOT-89, SC-62	B.C.E.C











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Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4
DCQ	2SD1767	ROHM	прп	V_{CBD} = 80B; I_C = 700 mA; P_D = 500 mBT; h_{21} = 120270; f_T > 120 MFu	SOT-89, SC-62	B•C•E•C
DCR	2SD1767	ROHM	прп	V_{CB0} = 80 B; I_C = 700 mA; P_D = 500 mB τ ; h_{21} = 180390; f_T > 120 M Γ u,	SOT-89, SC-62	B•C•E•C
DD	2SD1419	REN	npn	V _{CRD} = 120 B; I _C = 1 A; P _D = 1 Bт; h _M = 60120; f _T = 140 МГц	SOT-89, SC-62	B•C•E•C
DD	BFN16	SIEM	npn	$V_{CB0} = 250B$; $I_C = 200 \text{ mA}$; $P_D = 1 \text{ BT}$; $h_{21} > 40$; $f_T > 70 \text{ MF} \text{ U}$	SOT-89, SC-62	B•C•E•C
DDP	2SD1766	ROHM	npn	$V_{CBO} = 40B$; $I_C = 2A$; $P_D = 500 \text{ mBT}$; $h_{21} = 82180$; $f_T > 100 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
DDQ	2SD1766	ROHM	npn	$V_{CB0} = 40B$; $I_C = 2A$; $P_D = 500 \text{ MB}_T$; $h_{21} = 120270$; $f_T > 100 \text{ MF}_U$	SOT-89, SC-62	B•C•E•C
DDR	2SD1766	ROHM	npn	$V_{CR0} = 40B$; $I_C = 2A$; $P_D = 500 \text{ mB}_T$; $h_{21} = 180390$; $f_T > 100 \text{ MF}_U$	SOT-89, SC-62	B•C•E•C
DE	2SD1419	REN	non	V _{CBD} = 120B; I _C = 1 A; P _D = 1 Bт; h ₂₁ = 100200; f _T = 140 МГц	SOT-89, SC-62	B•C•E•C
DE	2SD1834	ROHM	non	V _{CR0} = 60B; I _C = 1A; P _D = 500 MBT; h ₂₁ > 2000	SOT-89, SC-62	B•C•E•C
DE	BFN18	SIEM	npn	$V_{CR0} = 300B$; $I_C = 200 \text{ mA}$; $P_D = 1 \text{ BT}$; $h_{21} > 30$; $f_T > 70 \text{ MF}$ u	SOT-89, SC-62	B•C•E•C
DF	2SD1898	ROHM	non	V _{CB0} = 80B; I _C = 1A; P _D = 2Bт; h ₂₁ = 82390; f _T > 100 МГц	SOT-89, SC-62	B•C•E•C
DF	BF621	PHIL	prp	V _{CBD} = 300 B; I _C = 50 mA; P _D = 1 BT; h ₂₁ > 50; f _T > 60 MF _U	SOT-89, SC-62	B•C•E•C
DF	BF721T1	ON	pnp	V _{CB} =300 B; I _C =100 мА; P _D =1.5 Вт; h ₂₁ >50; f _T =60 МГц	SOT-223, TO-261AA	B•C•E•C
DF	BFN21	SIEM	pnp	V _{CR0} =300B; I _C =50мA; P _D =1Bт; h ₂₁ >40; f _T =100МГц	SOT-89, SC-62	B•C•E•C
DG	BFN17	SIEM	pnp	V _{CR0} = 250B; I _C = 200 mA; P _D = 1BT; h ₂₁ > 40; f _T = 100 MFu	SOT-89, SC-62	B•C•E•C
DGQ	2SD1963	ROHM	non	V _{CBD} = 50B; I _C = 3A; P _D = 500 MBT; h ₂₁ = 120270; f _T > 150 MFu	SOT-89, SC-62	B•C•E•C
DGR	2SD1624R	SANYO		V _{CB0} = 60 B; I _C = 3 A; P _D = 500 mBr; h ₂₁ = 100200; f _T = 150 MFu.	SOT-89, SC-62	B•C•E•C
DGR	2SD1963	ROHM	non	V _{CB0} = 50B; I _C = 3 A; P _D = 500 MBT; h ₂₁ = 180390; f _T > 150 MF _U	SOT-89, SC-62	B•C•E•C
DGS	2SD1624S	SANYO		V _{CR0} =60B; I _C =3A; P _D =500 мВт; I ₂₁ =140280; f _T =150МГц	SOT-89, SC-62	B•C•E•C
DGS	2SD1963	ROHM	npn	V _{CPD} =50B; I _C =3A; P _D =500 MBT; I _{P2} =270560; I _T >150 MF _U	SOT-89, SC-62	B•C•E•C
DGT	2SD1624T	SANYO		V _{CPD} =60B; I _C =3A; P _D =500 MBT; I _{D1} =270300; I _T =150 MFц	SOT-89, SC-62	B•C•E•C
DGU	2SD1624U	SANYO	1.	V _{CBD} =60B; I _C =3A; P _D =500 MBT; I _{D1} =280560; I _T =150 MFц	SOT-89, SC-62	B•C•E•C
DH	2SB1025DH	REN	pnp	V _{CB0} = 120B; I _C = 1A; P _D = 1BT; h _{Pl} = 60120; f _T = 140 MFu	SOT-89, SC-62	B•C•E•C
DH	2SD1625DH	SANYO		V _{CB0} =80B; I _C =700 MA; P _D =500 MBT; I ₂₁ >5000; I _T =200 MFц	SOT-89, SC-62	B•C•E•C
DH	BFN19	SIEM		V _{CB0} = 300 B; I _C = 200 MA; P _D = 30 MB1; I _{P1} > 3000; I _T = 200 MΓ _Q V _{CB0} = 300 B; I _C = 200 MA; P _D = 1 BT; I _{P1} > 30; I _T = 100 MΓ _Q	SOT-89, SC-62	B•C•E•C
DI	2SD1626	SANYO	pnp	V _{CB0} =80B; I _C =2.00MA, P _D =101, I _{D1} >30, I _T =100 MII μ V _{CB0} =80B; I _C =1.5 A; P _D =500 MBτ; h ₂₁ >4000; f _T =120 MΓμ	SOT-89, SC-62	B•C•E•C
D.I	2SB1025D.I	REN		V _{CB0} = 120B; I _C = 1.5A; P _D = 300 MB1; H ₂₁ > 4000; η = 120 MII _L V _{CB0} = 120B; I _C = 1 A; P _D = 1 BT; h ₂₁ = 100200; f _T = 140 MΓ _L	SOT-89, SC-62	B•C•E•C
DJO	2SD2098	ROHM	pnp	$V_{CB0} = 50B; I_C = 5A; P_D = 500 \text{ MBT}; I_{21} = 120270; I_T = 140 \text{ MFU}$	SOT-89, SC-62	B•C•E•C
DJR			npn	000	The state of the s	B•C•E•C
DJS	2SD2098	ROHM	npn	V _{CB0} = 50 B; I _C = 5 A; P _D = 500 MB _T ; h ₂₁ = 180390; f _T > 150 MF _U	SOT-89, SC-62 SOT-89, SC-62	B•C•E•C
DK	2SD2098	ROHM	npn	V _{CBD} =50B; I _C =5A; P _D =500 MBτ; h ₂₁ =270560; f _T >150 MΓц		
DKP	2SB1025DK 2SC4672	REN	pnp	V _{CB0} = 120B; I _C = 1 A; P _D = 1 BT; h ₂₁ = 160320; f _T = 140 MF _U	SOT-89, SC-62	B•C•E•C
DKQ			npn	V _{CB0} = 60 B; I _C = 2 A; P _D = 500 mBr; h ₂₁ = 82180; f _T > 210 MFu	SOT-89, SC-62	
DL	2SC4672	ROHM	npn	$V_{CBD} = 60B; I_C = 2A; P_D = 500 \text{ MBT}; h_{21} = 120270; f_T > 210 \text{ MFL}$	SOT-89, SC-62	B • C • E • C
DLN	2SB1026DL	REN	pnp	V _{CB0} = 120B; I _C = 1 A; P _D = 1 BT; h ₂₁ = 60120; f _T = 140 MF _{LL}	SOT-89, SC-62	B•C•E•C
	2SD2167	ROHM	npn	V _{CB0} = 31B; I _C = 2A; P _D = 500 mB _T ; h ₂₁ = 56120; f _T > 100 mF _L	SOT-89, SC-62	B•C•E•C
DLP	2SD2167	ROHM	npn	V _{CB0} =31B; I _C =2A; P _D =500 mB _T ; h ₂₁ =82180; f _T >100 MF _U	SOT-89, SC-62	B•C•E•C
DLQ	2SD2167	ROHM	npn	V _{CB0} =31B; I _C =2A; P _D =500 мВт; h ₂₁ =120270; f _T >100 МГц	SOT-89, SC-62	B•C•E•C
DM	2SB1026DM	REN	pnp	$V_{CB0} = 120B$; $I_C = 1$ A; $P_D = 1$ BT; $h_{21} = 100200$; $f_T = 140$ MF $_{II}$	SOT-89, SC-62	B•C•E•C
DM	2SD2170	ROHM	npn	$V_{O80} = 90 \text{ B; } I_C = 2 \text{ A; } P_D = 500 \text{ MBT; } h_{21} = 1000 \dots 10000; f_T > 80 \text{ MFu, } h_{21} = 1000 \text{ MFu, } h_{21} = 100000; f_T > 80 \text{ MFu, } h_{21} = 100000; f_T > 80 \text{ MFu, } h_{21} = 100000; f_T > 80 \text{ MFu, } h_{21} = 100000; f_T > 80 \text{ MFu, } h_{21} = 100000; f_T > 80 \text{ MFu, } h_{21} = 100000; f_T > 80 \text{ MFu, } h_{21} = 100000; f_T > 80 \text{ MFu, } h_{21} = 100000; f_T > 80 \text{ MFu, } h_{21} = 100000; f_T > 80 \text{ MFu, } h_{21} = 1000000; f_T > 80 \text{ MFu, } h_{21} = 100000; f_T > 80 \text{ MFu, } $	SOT-89, SC-62	B•C•E•C
DNE	2SD2153	ROHM	npn	$V_{CB0} = 30B$; $I_C = 2A$; $P_D = 500 \text{ mBT}$; $h_{21} = 390820$; $f_T > 110 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
DNU	2SD2153	ROHM	npn	V_{CB0} = 30 B; I_C = 2A; P_D = 500 mBT; h_{21} = 5601200; f_T > 110 MFu	SOT-89, SC-62	B•C•E•C
DNV	2SD2153	ROHM	npn	$V_{C80} = 30 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ MBT}; h_{21} = 8201800; f_T > 110 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
DNW	2SD2153	ROHM	npn	$V_{CB0} = 30 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ mBT}; h_{21} = 12002700; f_T > 110 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
DO	2SA1201	TOSH	pnp	$V_{CB0} = 120 \text{ B}; I_C = 800 \text{ mA}; P_D = 500 \text{ mBT}; h_{21} > 70140; f_T = 120 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
DP	2SD2195	ROHM	npn	$V_{C80} = 100 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ MBT}; h_{21} = 100010000; f_T > 80 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
DQN	2SD2211	ROHM	npn	$V_{CBO} = 160B$; $I_C = 1500 \text{ mA}$; $P_D = 500 \text{ mB}\text{T}$; $h_{21} = 56120$; $f_T > 80 \text{ M}\Gamma_U$	SOT-89, SC-62	B•C•E•C
DQP	2SD2211	ROHM	npn	$V_{CBO} = 160 \text{ B}; I_C = 1500 \text{ mA}; P_D = 500 \text{ mBT}; h_{21} = 82180; f_T > 80 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
DQQ	2SD2211	ROHM	npn	$V_{CBD} = 160 B$, $I_C = 1500 \text{ mA}$, $P_D = 500 \text{ mB} \text{T}$; $h_{21} = 120270$; $f_T > 80 \text{ MF}_{LI}$	SOT-89, SC-62	B•C•E•C









Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4
DR	2SC4643	REN	npn	V _{CRD} = 15 B; I _C = 50 мА; P _D = 400 мВт; h ₂₁ = 40250; f _T > 5.5 ГГц	SOT-89, SC-62	B•C•E•C
DR	2SD2212	ROHM	npn	$V_{CB0} = 60 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ MBT}; h_{21} = 100010000; f_T > 80 \text{ MF}_{\text{L}}$	SOT-89, SC-62	B•C•E•C
DTP	2SD2391	ROHM	npn	$V_{CB0} = 60 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ mBT}; h_{21} = 82180; f_T > 210 \text{ M}\Gamma_U$	SOT-89, SC-62	B•C•E•C
DTQ	2SD2391	ROHM	npn	$V_{CB0} = 60 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ mBT}; h_{21} = 120270; f_T > 210 \text{ MF}_{IJ}$	SOT-89, SC-62	B•C•E•C
DY	2SA1201	TOSH	pnp	V_{CE0} =120B; I_C =800mA; P_D =500mBT; h_{21} >120240; f_T =120MF χ	SOT-89, SC-62	B•C•E•C
E01	DTDG14EP	ROHM	Dnpn+ dz	V_{CB0} = 60 B; I_C = 1 A; P_D = 500 mBT; h_{21} > 300; f_T > 80 MFц; R_2 = 10 кОм	SOT-89, SC-62	B•C•E•C
E01	DTDG14GP	ROHM	Dnpn+ dz	$V_{CB0} = 60 \text{ B}; I_C = 1 \text{ A}; P_D = 500 \text{ MBT}; h_{21} > 300; f_T > 80 \text{ MFu}; R_2 = 10 \text{ kGM}$	SOT-89, SC-62	B•C•E•C
E02	DTDG23YP	ROHM	Dnpn+ dz	V_{C80} =60 B; I_C =1 A; P_D =1.5 BT; h_{21} >300; f_T =80 MFu; 2.2 к/10 к	SOT-89, SC-62	B•C•E•C
ED	2SD1421	REN	npn	V _{CB0} =180B; I _C =1.5A; P _D =1BT; h ₂₁ =60120	SOT-89, SC-62	B•C•E•C
ED	BCV28	INF	dpnp	$V_{CBD} = 40 \text{ B}; I_C = 500 \text{ mA}; P_D = 1 \text{ BT}; h_{21} > 100; f_T = 200 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
EE	2SD1421	REN	npn	V _{CR0} = 180B; I _C = 1.5A; P _D = 1Br; h ₂₁ = 100200	SOT-89, SC-62	B•C•E•C
EE	BCV48	INF	dpnp	$V_{CB0} = 80 \text{ B}; I_C = 500 \text{ mA}; P_D = 1 \text{ BT}; h_{21} > 400; f_T = 200 \text{ MF}_{\text{LL}}$	SOT-89, SC-62	B•C•E•C
EF	BCV29	INF	dnpn	$V_{CB0} = 40 \text{ B}; I_C = 500 \text{ mA}; P_D = 1 \text{ BT}; h_{21} > 100; f_T = 150 \text{ MF} \text{ µ}$	SOT-89, SC-62	B•C•E•C
EG	BCV49	INF	dnpn	V _{CBD} = 80 B; I _C = 500 мА; P _D = 1 Вт; h ₂₁ > 400; f _T = 150 МГц	SOT-89. SC-62	B•C•E•C
FL	2SB1028EL	REN	pnp	V _{CBO} = 180B; I _C = 1.5A; P _D = 1BT; h ₂₁ = 60120	SOT-89. SC-62	B•C•E•C
EM	2SB1028EM	REN	pnp	V _{CB0} = 180 B; I _C = 1.5 A; P _D = 1 Br; h ₂₁ = 100200	SOT-89, SC-62	B•C•E•C
ER	2SC4807	REN	ngn	V _{CRD} =20 B; I _C =200 MA; P _D =800 MBr; h ₂₁ =50250; f _T >3 ΓΓц	SOT-89, SC-62	B•C•E•C
FA	BFQ17	PHIL	ngn	V _{CB0} =40B; I _C =300 MA; P _D =1BT; h ₂₁ =85; f _T =1.5 ΓΓц	SOT-89, SC-62	B•C•E•C
FB	BFQ19	PHIL			SOT-89, SC-62	B•C•E•C
FC	BFQ64	SIEM	npn	V _{EBO} = 15 B; I _C = 100 mA; P _D = 1 BT; h ₂₁ > 25; f _T = 5.5 ΓΓц	SOT-89, SC-62	B•C•E•C
FD FD	EUSEU.		npn	I _C =200 мА; Р _D =1 Вт; h21 > 25; f _T > 3 ГГц		
_	BFQ17P	SIEM	npn	$V_{CB0} = 40 \text{ B}; I_C = 300 \text{ mA}; P_D = 1 \text{ BT}; h_{21} = 85; f_T = 1.5 \Gamma \Gamma_U$	SOT-89, SC-62	B•C•E•C
FEs	BFQ19P	SIEM	npn	$V_{CB0} = 15 \text{ B}; I_C = 100 \text{ mA}; P_D = 1 \text{ BT}; h_{21} > 25; f_T = 5.5 \text{ FT} \text{ L}$	SOT-89, SC-62	B•C•E•C
FF	BFQ18A	PHIL	прп	$V_{CB0} = 25 \text{ B}; I_C = 150 \text{ mA}; P_D = 1 \text{ BT}; h_{21} > 25; f_T = 4 \Gamma \Gamma I_L$	SOT-89, SC-62	B•C•E•C
FGs	BFQ19S	SIEM	npn	$V_{CB0} = 20 \text{ B}; I_C = 75 \text{ mA}; P_D = 1 \text{ BT}; h_{21} = 40220; f_T = 5500 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
FO	2SA1202	TOSH	pnp	$V_{CE0} = 80B$; $I_C = 400$ mA; $P_D = 500$ mBT; $h_{21} > 70140$; $f_T = 120$ MF $_U$	SOT-89, SC-62	B•C•E•C
FY	2SA1202	TOSH	pnp	$V_{CE0} = 80 B$; $I_C = 400 \text{ mA}$; $P_D = 500 \text{ mBT}$; $h_{21} > 120240$; $f_T = 120 \text{MFu}$.	SOT-89, SC-62	B•C•E•C
GA	BAW78A	SIEM	di	$V_n \le 50 \text{ B; } I_F \le 1 \text{ A; } V_F (I_F = 1 \text{ A}) \le 1.6 \text{ B; } I_R \le 1.0 \text{ mKA; } C_D \le 10 \text{ n}\Phi;$ $I_{RR} \le 1000 \text{ Hz}$	SOT-89, SC-62	A • K • n. c. • K
GB	BAW78B	SIEM	di	V_R < 100 B; I_F < 1 A; V_F (I_F = 1 A) < 1.6 B; I_R < 1.0 мкA; C_D < 10 п Φ ; I_{RR} < 1000 HC	SOT-89, SC-62	A • K • n. c. • K
GC	BAW78C	SIEM	di	V_R < 200 B; I_F < 1 A; V_F (I_F = 1 A) < 1.6 B; I_R < 1.0 мкA; C_D < 10 п Φ ; I_{RR} < 1000 HC	SOT-89, SC-62	A • K • n. c. • K
GD	BAW78D	SIEM	di	$V_R < 400B$; $I_F < 1A$; $V_F (I_F = 1A) < 1.6B$; $I_R < 1.0$ mKA; $C_D < 10$ n Φ ; $I_{RR} < 1000$ HC	SOT-89, SC-62	A • K • n. c. • K
GE	BAW79A	SIEM	dix2	$V_R < 50 B_i I_F < 1 A_i V_F (I_F = 1 A) < 1.6 B_i I_R < 1.0 \text{mKA}; C_O < 10 \text{n} \Phi; I_{RN} < 1000 \text{Hz}$	SOT-89, SC-62	A1 • K1, K2 • A2 • K1, K2
GF	BAW79B	SIEM	di x2	V_R < 100 B; I_F < 1 A; V_F (I_F = 1 A) < 1.6 B; I_R < 1.0 мкA; C_D < 10 п Φ ; I_{RR} < 1000 HC	SOT-89, SC-62	A1 • K1, K2 • A2 • K1, K2
GG	BAW79C	SIEM	di x2	V_R < 200 B; I_F < 1 A; V_F (I_F = 1 A) < 1.6 B; I_R < 1.0 mrA; C_D < 10 n Φ ; I_{RR} < 1000 HC	SOT-89, SC-62	A1 • K1, K2 • A2 • K1, K2
GH	BAW79D	SIEM	di x2	V_R < 400 B; I_F < 1 A; V_F (I_F = 1 A) < 1.6 B; I_R < 1.0 mrA; C_D < 10 n Φ ; I_{RR} < 1000 HC	SOT-89, SC-62	A1 • K1, K2 • A2 • K1, K2
GO	KTC4375	KEC	npn	V _{CBO} = 30 B; I _C = 1.5 A; P _D = 500 мВт; h ₂₁ = 100200; f _T > 120 МГц	SOT-89, SC-62	B•C•E•C
GY	KTC4375	KEC	npn	$V_{CB0} = 30 \text{ B}; I_C = 1.5 \text{ A}; P_D = 500 \text{ mBT}; h_{21} = 160320; f_T > 120 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
НО	2SA1203	TOSH	pnp	V _{CEO} = 30 B; I _C = 1.5 A; P _D = 500 мВт; h ₂₁ = 100200; f _T = 200 МГц	SOT-89, SC-62	B•C•E•C
НО	KTA1663	KEC	pnp	V _{CB0} = 30 B; I _C = 1.5 A; P _D = 500 мВт; h ₂₁ = 100200; f _T > 120 МГц	SOT-89, SC-62	B•C•E•C
HY	2SA1203	TOSH	pnp	V _{CE0} = 30 B; I _C = 1.5 A; P _D = 500 мBr; h ₂₁ > 160320; f _T = ы120 МГц	SOT-89, SC-62	B•C•E•C
HY	KTA1663	KEC	ono	V _{CR0} =30B; I _C =1.5A; P _D =500 mBT; h ₂₁ =160320; f _T >120 MFu	SOT-89, SC-62	B•C•E•C









SOT89 SOT223 TO252 TO263 DPAK TO263

Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3•4
JO	2SA1384	TOSH	npn	V _{CBO} = 300 B; I _C = 100 мА; P _D = 500 мВт; h ₂₁ > 50150; f _T > 50 МГц	SOT-89, SC-62	B•C•E•C
JR	2SA1384	TOSH	npn	$V_{CE0} = 300 \text{ B; } I_C = 100 \text{ mA; } P_D = 500 \text{ mBT; } h_{21} > 3090; f_T > 50 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
JR	2SC5631	REN	npn	V_{CBD} = 15B; I_C = 80 мA; P_D = 800 мВт; h_{21} = 80160; f_T > 8 ГГц	SOT-89, SC-62	B•C•E•C
JX	2SK3391	REN	nMOS	V _{DS} = 17 B; I _D = 300 mA; P _D = 5 BT	SOT-89, SC-62	G•S•D•S
K0	BST86	PHIL	nMOS	V _{DS} = 180 B; I _D = 300 мА; P _D = 1 Вт; R _{DS(on)} = 7 Ом	SOT-89, SC-62	S•D•G•D
KA	2SC4409	TOSH	npn	$V_{CEO} = 80B$; $I_C = 2A$; $P_D = 500 \text{ mBT}$; $h_{21} > 120400$; $f_T = 100 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
KA	BSS87	SIEM	nMOS	V _{DS} = 240 B; I _D = 290 мА; P _D = 1 Вт; g _F = 50мс; R _{DS} = 10 Ом	SOT-89, SC-62	G•D•S•D
KB	2SC4539	TOSH	npn	$V_{CE0} = 30 \text{ B; } I_C = 1.2 \text{ A; } P_0 = 500 \text{ mBT; } h_{21} = 120400; f_T = 100 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
KB	BSS192	INF	pMOS	V _{DS} = 240 B; I _D = 150 mA; P _D = 1 BT; g _F = 120 mCm; R _{DS} = 3.5 Om	SOT-89, SC-62	G•D•S•D
KC	2SC4540	TOSH	npn	$V_{CEO} = 50B$; $I_C = 1A$; $P_D = 500 \text{ mBT}$; $h_{21} = 120400$; $f_T = 100 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
KD	2SC4541	TOSH	npn	$V_{CE0} = 50 \text{ B; } I_C = 3 \text{ A; } P_D = 1500 \text{ mBt; } h_{21} > 120400; f_T = 100 \text{ MFu},$	SOT-89, SC-62	B•C•E•C
KM	BST80	PHIL	nMOS	V _{DS} = 80 B; I _D = 500 мА; P _D = 1 Вт; R _{DS(en)} = 3 Ом	SOT-89, SC-62	S•D•G•D
KM	BST80	ZETEX	nMOS	V _{DS} = 80 B; I _D = 500 мА; P _D = 1 Вт; R _{DS(on)} = 3 Ом	SOT-89, SC-62	S•D•G•D
KN	BST84	PHIL	nMOS	V _{DS} = 200 B; I _D = 250 mA; P _D = 1 BT; R _{DS(on)} = 6 Om	SOT-89, SC-62	S•D•G•D
LA	2SC1681	TOSH	pnp	$V_{CEO} = 60B$; $I_C = 2A$; $P_D = 500 \text{ mBT}$; $h_{21} > 120400$; $f_T = 100 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
LA	KTD1003	KEC	npn	$V_{CB0} = 60 \text{ B}; I_C = 1.0 \text{ A}; P_D = 500 \text{ mBT}; h_{21} = 8001600; f_T > 250 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
LB	2SC1734	TOSH	prip	$V_{CE0} = 40 \text{ B}; I_C = 1.2 \text{A}; P_0 = 500 \text{ mBT}; h_{21} > 120400; f_T = 100 \text{ MFU}$	SOT-89, SC-62	B•C•E•C
LB	KTD1003	KEC	npn	V_{CB0} =60B; I_C =1.0A; P_D =500 mBT; h_{21} =12002400; f_T >250 M Γ_{II}	SOT-89, SC-62	B•C•E•C
LC	2SC1735	TOSH	pnp	$V_{CEO} = 60B$; $I_C = 1.A$; $P_D = 500 \text{ mBT}$; $h_{21} > 120400$; $f_T = 100 \text{ M}\Gamma_{IJ}$	SOT-89, SC-62	B•C•E•C
LC	KTD1003	KEC	npn	$V_{CB0} = 60 \text{ B}; I_C = 1.0 \text{ A}; P_D = 500 \text{ mB} \text{ T}; h_{21} = 20003200; f_T > 250 \text{ M} \Gamma_U$	SOT-89, SC-62	B•C•E•C
LD	2SC1736	TOSH	pnp	$V_{CED} = 60B$; $I_C = 3A$; $P_D = 500 \text{ mBT}$; $h_{21} > 120400$; $f_T = 100 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
LM	BST120	PHIL	pMOS	V _{DS} = 60 B; I _D = 300 mA; P _D = 1 BT; g _F = 200 mCm; P _{DS(on)} = 4.5 Om	SOT-89, SC-62	S•D•G•D
LN	BST122	PHIL	pMOS	V _{DS} = 60 B; I _D = 250 mA; P _D = 1 BT; g _F = 125 mCm; R _{DS(m)} = 7.5 Om	SOT-89, SC-62	S•D•G•D
LYD	2SC4003D	SANYO	non	V _{CP0} =400B; I _C =200 мА; P _D =1BT; h _{P1} =60120; f _T =70 МГц	TO-252, DPAK	B•C•E•C
LYE	2SC4003E	SANYO	non	V _{CBD} = 400 B; I _C = 200 мА; P _D = 1 Bт; h _{P1} = 100200; f _T = 70 МГц	TO-252, DPAK	B•C•E•C
N01	DTDM12ZP	ROHM	Dnpn+ dz	$V_{CBO} = 30B; I_C = 3A; P_D = 500 \text{ mB}_T; h_{21} > 68; f_T > 80 \text{ MF}_U$	SOT-89, SC-62	B•C•E•C
p1A	PXT3904	PHIL	npn	$V_{CBD} = 60B$; $I_C = 200 \text{ mA}$; $P_D = 1BT$; $h_{21} = 100300$; $f_T > 300 \text{ MF}_{LL}$	SOT-89, SC-62	B•C•E•C
p1B	PXT2222	PHIL	non	V _{CB0} = 60 B; I _C = 600 мА; P _D = 1 Вт; h ₂₁ = 100300; f _T > 250 МГц	SOT-89, SC-62	B•C•E•C
p1D	PXTA42	PHIL	npn	$V_{CBD} = 300B$; $I_C = 500 \text{ mA}$; $P_D = 1B_T$; $h_{21} > 40$; $f_T > 50 \text{ M/L}$	SOT-89, SC-62	B•C•E•C
P1D	PZTA42	MOT	non	V _{CBD} =300B; I _C =500мA; P _D =1.5 Bт; h ₂₁ >25; f _T >50МГц	SOT-223, TO-261AA	B•C•E•C
p1E	PXTA43	PHIL	non	V _{CPD} = 200B; I _C = 500 MA; P _D = 1BT; h ₂₁ > 40; f _T > 50 MFu	SOT-89, SC-62	B•C•E•C
P1F	PZT2222A	ON	non	V _{CR0} = 75B; I _C = 600 MA; P _D = 1.5BT; h ₂₁ = 50300; f _T > 300 MF _U	SOT-223, TO-261AA	B•C•E•C
o1M	PXTA13	PHIL	dnpn	$V_{CPD} = 30B$; $I_C = 500 \text{ mA}$; $P_D = 625 \text{ mBT}$; $h_{21} > 5000$; $f_T > 125 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
p1N	PXTA14	PHIL	dnpn	V _{CR0} = 30B; I _C = 300 мА; P _D = 1 Вт; h ₂₁ > 20000; f _T > 125 МГц	SOT-89, SC-62	B•C•E•C
P1N	PZTA14	MOT	dnpn	V _{CE0} =30B; I _C =300мA; P _D =1.5Bт; h ₂₁ >10000; f _T >125МГц	SOT-223, TO-261AA	B•C•E•C
p1P	PXT2222A	PHIL	npn	V _{CP0} = 75B; I _C = 600 mA; P _D = 1BT; h ₂₁ = 100300; f _T > 300 MF _U	SOT-89, SC-62	B•C•E•C
p2A	PXT3906	PHIL	pnp	V _{CBD} =40B; I _C =200 MA; P _D =1BT; h ₂₁ =100300; f _T >250 MFu	SOT-89, SC-62	B•C•E•C
p2B	PXT2907	PHIL	pnp	V _{CBD} = 60B; I _C = 600 MA; P _D = 1BT; h ₂₁ = 100300; f _T > 200 MFu	SOT-89, SC-62	B•C•E•C
p2D	PXTA92	PHIL	pnp	V _{CR0} = 300 B; I _C = 500 mA; P _D = 1 BT; h _{P1} > 40; f _T > 50 MFu	SOT-89, SC-62	B•C•E•C
P2D	PZTA92	MOT	pnp	V _{CB0} =300B; I _C =500mA; P _D =1.5BT; h _{P1} >25; f _T >50MFu	SOT-223, TO-261AA	B•C•E•C
p2E	PXTA93	PHIL	pnp	V _{CB0} =200B; I _C =500mA; P _D =1BT; h ₂₁ >40; f _T >50MFu	SOT-89, SC-62	B•C•E•C
p2F	PXT2907A	PHIL	pnp	V _{CPD} = 60B; I _C = 600 mA; P _D = 1BT; h ₂₁ = 100300; f _T > 200 MF _U	SOT-89, SC-62	B•C•E•C
P2F	PZT2907A	ON	pnp	V _{CBO} = 60 B; I _C = 600 мA; P _D = 1.5 Bт, h ₂₁ = 100300; f ₁ > 200 МГц		B•C•E•C
o2T	PXT4403	PHIL	prip	V _{CPD} = 40B; I _C = 600 mA; P _D = 1BT; I _D = 100300; f _T > 200 MF _L	SOT-89, SC-62	B•C•E•C
p2V	PXTA64	PHIL	prip	V _{CB0} =30B; I _C =300 MA; P _D =1BT; h ₂₁ >10000; f _T >125 MF _U	SOT-89, SC-62	B•C•E•C
P2V	PZTA64	MOT	dpnp	V _{CB0} =30B; I _C =500 мA; P _D =1.5Bτ; h ₂₁ > 10000; f ₇ > 125 MΓц	SOT-223, TO-261AA	B•C•E•C
V				V _{CBD} =40B; I _C =600 MA; P _D =1BT; h ₂₁ =100300; f _T >250 MF _U	SOT-89, SC-62	B•C•E•C
n2X	PX (440)					
p2X PO	PXT4401 KTC4376	PHIL	npn	$V_{CB0} = 35 B$; $I_C = 0.8 A$; $P_D = 500 \text{ MBT}$; $I_{P2} = 100200$; $I_T > 120 \text{ MFL}$	SOT-89, SC-62	B•C•E•C





SOT223



SOT89



Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3•4
R111718	REG1117A-1.8	TI	reg	LDO; I _{OUT} = 1 A; V _{OUT} = 1.8 B	SOT-223, TO-261AA	GND • VOUT • VIN • VOUT
R111725	REG1117A-2.5	TI	reg	LDO; I _{OUT} = 1 A; V _{OUT} = 2.5 B	SOT-223, TO-261AA	GND • VOUT • VIN • VOUT
RCs	BFQ193	SIEM	npn	V_{CBD} =20B; I_C =80 MA; P_D =600 MBT; h_{21} =50200; f_T =7500 M Γ_{LI}	SOT-89, SC-62	B•C•E•C
RE	2SC3357E	NEC	npn	$V_{CB0} = 20 \text{ B}; I_C = 100 \text{ mA}; P_D = 1.2 \text{ BT}; h_{21} = 125250; f_T = 6.5 \Gamma\Gamma \text{ G}$	SOT-89, SC-62	B•C•E•C
REG1117F A	REG1117FA	TI	reg	LDO; I _{OUT} = 1 A; V _{REF} = 1.25 B	TO-263, D2PAK	ADJ • VOUT • VIN • VOUT
REG1117F A1.8	REG1117FA- 1.8	TI	reg	LDO; I _{OUT} = 1 A; V _{OUT} = 1.8 B	TO-263, D2PAK	GND • VOUT • VIN • VOUT
REG1117F A2.5	REG1117FA- 2.5	TI	reg	LDO; I _{OUT} = 1 A; V _{OUT} = 2.5 B	TO-263, D2PAK	GND • VOUT • VIN • VOUT
REG1117F A5.0	REG1117FA-5	TI	reg	LDO; I _{OUT} = 1 A; V _{OUT} = 5 B	TO-263, D2PAK	GND • VOUT • VIN • VOUT
RF	2SC3357F	NEC	ngn	V _{CBD} = 20 B; I _C = 100 mA; P _D = 1.2 BT; h ₂₁ = 80160; f _T = 6.5 FFu	SOT-89, SC-62	B•C•E•C
RH	2SC3357H	NEC	npn	V _{DB0} = 20 B, I _C = 100 мА, P _D = 1.2 Bт, h ₂₁ = 50100, f _T = 6.5 ГГц	SOT-89, SC-62	B•C•E•C
BO	2SA1204	TOSH	pnp	V _{CRI} = 35 B; I _C = 800 MA; P _D = 500 MBT; h _{Pl} > 100200; f _T = 120 MF _U	SOT-89, SC-62	B•C•E•C
BO	KTA1664	KEC	pnp	V _{CR0} = 35 B; I _C = 0.8A; P _D =500 MBT; h _{P1} =100200; f _T > 120 MFu	SOT-89, SC-62	B•C•E•C
RY	2SA1204	TOSH	pnp	V _{GF0} = 35 B; I _C = 800 MA; P _D = 500 MBT; h ₂₁ > 160320; f _T = 120 MF _U	SOT-89, SC-62	B•C•E•C
RY	KTA1664	KEC	pnp	V _{CR0} = 35 B; I _C = 0.8 A; P _D = 500 MBT; h ₂₁ = 160320; f _T > 120 MFц	SOT-89, SC-62	B•C•E•C
SA	2SC2982	TOSH	npn	V _{CE0} = 30 B; I _C = 2 A; P _D = 500 мВт; h ₂₁ = 140240; f _T = 140МГц	SOT-89, SC-62	B•C•E•C
SB	2SC2982	TOSH	npn	V _{DED} = 30B; I _C = 2A; P _D = 500 мВт; h ₂₁ = 200330; f _T = 140 МГц	SOT-89, SC-62	B•C•E•C
SC	2SC2982	TOSH	npn	V _{CEO} = 30B; I _C = 2A; P _D = 500 мВт; h ₂₁ = 300450; f _T = 140 МГц	SOT-89, SC-62	B•C•E•C
SCO	KSC2881	SAMS	non	V _{CR0} = 120 B; I _C = 800 mA; P _D = 500 mB _T ; h ₂₁ = 80160; f _T > 120 MF _U	SOT-89, SC-62	B•C•E•C
SCY	KSC2881	SAMS	npn	V_{CBI} = 120 B; I_C = 800 MA; P_D = 500 MBT; h_{P1} = 120240; f_T > 120 MFu.	SOT-89, SC-62	B•C•E•C
SD	2SC2982	TOSH	npn	V _{CE0} = 30B; I _C = 2A; P _D = 500мВт; h ₂₁ = 420600; f _T = 140МГц	SOT-89, SC-62	B•C•E•C
SDO	KSA1201	SAMS	pnp	V _{GPO} = 120 B; I _G = 800 mA; P _D = 500 mBT; h ₂₁ = 80160; f _T > 120 MFu	SOT-89, SC-62	B•C•E•C
SDO	KSA1203	SAMS	pnp	V _{CR0} =30B; I _C =1.5A; P _D =500 мВт; h ₂₁ =100200; f _T >120МГц	SOT-89, SC-62	B•C•E•C
SDY	KSA1201	SAMS	pnp	$V_{CB0} = 120B$; $I_C = 800$ mA; $P_D = 500$ mBT; $h_{21} = 120240$; $f_T > 120$ mF $_{II}$	SOT-89, SC-62	B•C•E•C
SDY	KSA1203	SAMS	pnp	V _{CBO} = 30 B; I _C = 1.5 A; P _D = 500 мВт; h ₂₁ = 160320; f _T > 120 МГц	SOT-89, SC-62	B•C•E•C
SE	NE46234	NEC	npn	СВЧ; NF=2.3 дБ; h ₂₁ =125250	SOT-89, SC-62	B•C•E•C
SE	NE462M02	NEC	npn	CB4; h ₂₁ = 125250	SOT-89, SC-62	B•C•E•C
SF	NE46234	NEC	npn	CB4; NF=2.3дБ; h ₂₁ =80160	SOT-89, SC-62	B•C•E•C
SF	NE462M02	NEC	npn	CB4; h ₂₁ = 80160	SOT-89, SC-62	B•C•E•C
SH	NE46234	NEC	npn	CB4; NF=2.3дБ; h ₂₁ =50100	SOT-89, SC-62	B•C•E•C
SH	NE462M02	NEC	npn	CB4; h ₂₁ = 50100	SOT-89, SC-62	B•C•E•C
SHO	KSC2883	SAMS	npn	V_{CB0} =30 B; I_C =1500 mA; P_D =500 mBT; h_{21} =100200; f_T >120 M Γ_{IJ}	SOT-89, SC-62	B•C•E•C
SHY	KSC2883	SAMS	npn	V_{CB0} =30 B; I_C =1500 mA; P_D =500 mBT; h_{21} =160320; f_T >120 M $\Gamma_{\rm U}$	SOT-89, SC-62	B•C•E•C
SLG	KSB798	SAMS	pnp	$V_{CB0} = 30 \text{ B}; I_C = 1 \text{ A}; P_D = 2 \text{ Br}; h_{21} = 200400; f_T > 110 \text{ MFц}$	SOT-89, SC-62	B•C•E•C
SLO	KSB798	SAMS	pnp	$V_{080} = 30 \text{ B}; I_C = 1 \text{ A}; P_D = 2 \text{ Br}; h_{21} = 90180; f_T > 110 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
SLY	KSB798	SAMS	pnp	$V_{CB0} = 30 \text{ B}; I_C = 1 \text{ A}; P_D = 2 \text{ Br}; h_{21} = 135270; f_T > 110 \text{ MF}_U$	SOT-89, SC-62	B•C•E•C
SSA	KSC2982	SAMS	npn	$V_{CB0} = 30 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ mBT}; h_{21} = 140240; f_T > 150 \text{ MF} \text{ L}$	SOT-89, SC-62	B•C•E•C
SSB	KSC2982	SAMS	npn	$V_{CB0} = 30 \text{ B}, I_C = 2 \text{ A}; P_D = 500 \text{ MBT}; h_{21} = 200330; f_T > 150 \text{ MF} \text{ L}$	SOT-89, SC-62	B•C•E•C
SSC	KSC2982	SAMS	npn	$V_{CB0} = 30 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ MBT}; h_{21} = 300450; f_T > 150 \text{ M}\Gamma_{IJ}$	SOT-89, SC-62	B•C•E•C
SSD	KSC2982	SAMS	npn	V_{CBD} =30 B; I_C =2A; P_D =500 mBT; h_{21} =420600; f_T >150 MF $_{II}$	SOT-89, SC-62	B•C•E•C
SYR	KSD1621	SAMS	npn	$V_{CB0} = 30 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ MBT}; h_{21} = 100200; f_T > 150 \text{ MFц}$	SOT-89, SC-62	B•C•E•C











Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4
SYS	KSD1621	SAMS	non	V _{CR0} = 30B; I _C = 2A; P _D = 500 MBT; h ₂₁ = 140280; f _T > 150 MFu	SOT-89, SC-62	B•C•E•C
SYT	KSD1621	SAMS	npn	$V_{CBD} = 30B$; $I_C = 2A$; $P_D = 500 \text{ MBH}$; $I_{D1} = 140200$; $f_T > 150 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
SYU	KSD1621	SAMS	non	V _{CPD} = 30B; I _C = 2A; P _D = 500 MBr; I _{D1} = 280560; I _T > 150 MFц	SOT-89, SC-62	B•C•E•C
SZR	KSB1121	SAMS	pnp	V _{CR0} =30B; I _C =2A; P _D =500 MBT; I _{D1} =100200; f _T >150 MF _U	SOT-89, SC-62	B•C•E•C
SZS	KSB1121	SAMS	pnp	V _{CR0} =30B; I _C =2A; P _D =500 MBT; I ₂₁ =140280; f _T >150 MFu	SOT-89, SC-62	B•C•E•C
SZT	KSB1121	SAMS	pnp	V _{CR0} =30B; I _C =2A; P _D =500 мВт; I ₂₁ =200400; f _T >150 МГц	SOT-89, SC-62	B•C•E•C
SZU	KSB1121	SAMS	pnp	V _{CBD} = 30B; I _C = 2 A; P _D = 500 MBT; h ₂₁ = 280560; f _T > 150 MFu	SOT-89, SC-62	B•C•E•C
T09A	MC33464N- 09AT1	ON	mrc	V _{TR} =0.9B; V _{IN} =0.710B	SOT-89, SC-62	RESET ● IN ● GND ● IN
T09C	MC33464N- 09CT1	ON	mrc	V _{TR} = 0.9 B; V _{IN} = 0.710 B	SOT-89, SC-62	RESET ● IN ● GND ● IN
T20A	MC33464N- 20AT1	ON	mrc	V _{TR} =2.0 B; V _{IN} =0.710 B	SOT-89, SC-62	RESET ● IN ● GND ● IN
T20C	MC33464N- 20CT1	ON	mrc	V _{TR} =2.0 B; V _{IN} =0.710 B	SOT-89, SC-62	RESET • IN • GND • IN
T27A	MC33464N- 27AT1	ON	mrc	V _{TR} =2.7B; V _{IN} =0.710B	SOT-89, SC-62	RESET ● IN ● GND ● IN
T27C	MC33464N- 27CT1	ON	mrc	V _{TR} =2.7B; V _{IN} =0.710B	SOT-89, SC-62	RESET ● IN ● GND ● IN
T30A	MC33464N- 30AT1	ON	mrc	V _{TR} = 3.0 B; V _{IN} = 0.710 B	SOT-89, SC-62	RESET ● IN ● GND ● IN
T30C	MC33464N- 30CT1	ON	mrc	V _{TR} = 3.0 B; V _{IN} = 0.710 B	SOT-89, SC-62	RESET ● IN ● GND ● IN
T43C	MC33464N- 43CT1	ON	mrc	V _{TR} =4.3 B; V _{IN} =0.710 B	SOT-89, SC-62	RESET • IN • GND • IN
T45A	MC33464N- 45AT1	ON	mrc	V _{TR} =4.5 B; V _{IN} =0.710 B	SOT-89, SC-62	RESET ● IN ● GND ● IN
T45C	MC33464N- 45CT1	ON	mrc	V _{TR} = 4.5 B; V _{IN} = 0.710 B	SOT-89, SC-62	RESET • IN • GND • IN
TA	2SA1314	TOSH	pnp	$V_{CE0} = 20B$; $I_C = 2A$; $P_D = 500 \text{ mBT}$; $h_{21} > 140280$; $f_T = 140 \text{ MFL}$	SOT-89, SC-62	B•C•E•C
TB	2SA1314	TOSH	pnp	$V_{CE0} = 20B$; $I_C = 2A$; $P_D = 500 \text{ mB}\text{T}$; $h_{21} > 200400$; $f_T = 140 \text{ M}\Gamma\text{L}$	SOT-89, SC-62	B•C•E•C
TC	2SA1314	TOSH	pnp	$V_{CE0} = 20B$; $I_C = 2A$; $P_D = 500 \text{ mBT}$; $h_{21} > 300600$; $f_T = 140 \text{ M}\Gamma_{U}$	SOT-89, SC-62	B•C•E•C
VD	1SV268	SANYO	pin	V _R >50 B; I _E < 100 mA; V _E (I _E =100 mA)<1 B; I _R <0.5 mkA	SOT-89, SC-62	A • K • n. c. • K
VO	2SC3803	TOSH	npn	$V_{CE0} = 45B$; $I_C = 200 \text{ mA}$; $P_D = 1 \text{ BT}$; $h_{21} > 70140$; $f_T > 100 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
VR	2SC3803R	TOSH	npn	V_{CED} = 45B; I_C = 200 mA; P_D = 1BT; h_{21} > 4080; f_T > 100 MF $_{II}$	SOT-89, SC-62	B•C•E•C
VY	2SC3803Y	TOSH	npn	$V_{CE0} = 45B$; $I_C = 200 \text{ mA}$; $P_0 = 1 \text{ B}\text{T}$; $h_{21} > 140280$; $f_T > 100 \text{ M}\Gamma_{\text{LL}}$	SOT-89, SC-62	B•C•E•C
VY W8	2SC3803Y BZV49C3V9	TOSH	npn dz	V_{CE0} =45B; I_C =200mA; P_D =1BT; I_{D1} >140280; I_T >200 MF I_T $V_Z(I_{ZT}$ =5.0mA)=3.74.1B; $Z_{ZT}(I_{ZT}$ =5.0mA)<900m;	SOT-89, SC-62 SOT-89, SC-62	B•C•E•C A•K•A•K
W9	BZV49C4V3	ZETEX	dz	$I_{ZM} = 250 \text{ mA}$ $V_Z(I_{ZT} = 5.0 \text{ mA}) = 4.04.6B; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 900 \text{m};$	SOT-89, SC-62	A•K•A•K
WO	2SA14830	TOSH	pnp	$I_{2M} = 250 \text{ MA}$ $V_{CBQ} = 60 \text{ B}; I_C = 200 \text{ MA}; P_D = 500 \text{ MBT}; h_{21} = 70140;$	SOT-89, SC-62	B•C•E•C
	00111000	70011		f ₇ = 200 MF ₄	007.00.00.00	
WR WY	2SA1483R 2SA1483Y	TOSH	pnp	$V_{CB0} = 60B$; $I_C = 200 \text{ mA}$; $P_D = 500 \text{ mB} \text{T}$; $h_{21} = 4080$; $f_T = 200 \text{ MF} \text{U}$ $V_{CB0} = 60B$; $I_C = 200 \text{ mA}$; $P_D = 500 \text{ mB} \text{T}$; $h_{21} = 120240$;	SOT-89, SC-62 SOT-89, SC-62	B•C•E•C
WY	2SJ484	REN	pMOS	$f_T = 200 \text{ MFu}$ $V_{DS} = 30 \text{ B; } I_D = 2 \text{ A; } P_D = 1 \text{ BT; } R_{DS(on)} \le 0.23 \text{ Om}$	SOT-89, SC-62	G•D•S•D
X2	BZV49C30	ZETEX	dz	$V_{Z}(I_{ZT}=2.0 \text{ mA}) = 28.032.0 \text{ B; } Z_{ZT}(I_{ZT}=2.0 \text{ mA}) < 800 \text{m;}$	SOT-89, SC-62	A•K•A•K
				I _{ZM} = 250 mA		
X5	BZV49C39	ZETEX	dz	$V_Z(I_{ZT}=2.0 \text{ mA}) = 37.041.0 \text{ B}; Z_{ZT}(I_{ZT}=2.0 \text{ mA}) < 130 \text{ Om}; $ $I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A∙K∙A∙K
X6	BZV49C43	ZETEX	dz	V_Z (I_{ZT} = 2.0 mA) = 40.046.0 B; Z_{ZT} (I_{ZT} = 2.0 mA) < 150 Om; I_{ZM} = 250 mA	SOT-89, SC-62	A•K•A•K
XC	RN5003	TOSH	Dnpn	$V_{CB0} = 30B$; $I_C = 2A$; $P_D = 500 \text{ mBT}$; $f_T = 120 \text{ MFu}$; $R_1 = 10 \text{ kOm}$	SOT-89, SC-62	B•C•E•C
Y 1	BZV49C11	ZETEX	dz	$V_Z(I_{ZT}=5.0 \text{ mA}) = 10.411.6 \text{ B; } Z_{ZT}(I_{ZT}=5.0 \text{ mA}) < 20 \text{ Om; } I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K



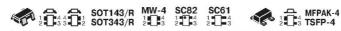








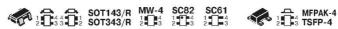
Код	Типономинал	6	Φ	Особенности	Kopnyc	Ц: 1•2•3•4
Y4	BZV49C15	ZETEX	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 13.815.6 \text{ B}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 30 \text{ Om}; I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
Y5	BZV49C16	ZETEX	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 15.317.1 \text{ B}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 40 \text{ Om};$ $I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
Y8	BZV49C22	ZETEX	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 20.823.3 \text{ B}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 55 \text{ Om};$ $I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
Y9	BZV49C24	ZETEX	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 22.825.6 \text{ B}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 70 \text{ Om};$ $I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
YA	RN6001	TOSH	Dnpn	$V_{CBO} = 30 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ mBt}; f_T = 120 \text{ MFu}; R_1 = 2 \text{ kOm}$	SOT-89, SC-62	B•C•E•C
YB	2SK680A	NEC	nMOS	V _{DS} = 30B; I _D = 1A; P _D = 2Bт; R _{DS/opt} < 1 Ом	SOT-89, SC-62	S•D•G•D
YB	RN6002	TOSH	Dnpn	$V_{CBO} = 30 \text{ B}; I_C = 2 \text{ A}; P_D = 500 \text{ mBr}; f_T = 120 \text{ MFu}; R_1 = 5.6 \text{ kOm}$	SOT-89, SC-62	B•C•E•C
YK	2SB1115K	NEC	pnp	V _{CB0} =60 B; I _C =1 A; P ₀ =2 BT; h ₂₁ =300600; f _T >80 MF _{LI}	SOT-89, SC-62	B•C•E•C
YL	2SB1115L	NEC	pnp	$V_{CB0} = 60 \text{ B}; I_C = 1 \text{ A}; P_D = 2 \text{ BT}; h_{21} = 200400; f_T > 80 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
YM	2SB1115M	NEC	pnp	$V_{CB0} = 60 \text{ B}; I_C = 1 \text{ A}; P_D = 2 \text{ BT}; h_{21} = 135270; f_T > 80 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
ΥP	2SB1115AP	NEC	pnp	$V_{CB0} = 80 \text{ B}; I_C = 1 \text{ A}; P_D = 2 \text{ BT}; h_{21} = 200400; f_T > 80 \text{ MFu}$	SOT-89, SC-62	B•C•E•C
YQ	2SB1115AQ	NEC	pnp	$V_{CB0} = 80 \text{ B}; I_C = 1 \text{ A}; P_D = 2 \text{ B}_T; h_{21} = 135270; f_T > 80 \text{ M}\Gamma_U$	SOT-89, SC-62	B•C•E•C
Z1	BZV49C10	ZETEX	dz	$V_Z(I_{ZT}=5.0 \text{ mA}) = 9.410.6 \text{ B}; Z_{ZT}(I_{ZT}=5.0 \text{ mA}) < 20 \text{ Om};$ $I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
Z1	BZV49C4V7	ZETEX	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 4.45.0 \text{B}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 80 \text{ Cm}; I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
Z2	BZV49C5V1	ZETEX	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 4.85.4 \text{B}; Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 60 \text{ Cm}; I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
Z3	2SK1078	TOSH	nMOS	V _{DS} = 60 B; I _D = 800 mA; P _D = 500 mBT; R _{DS(on)} < 1.10 m	SOT-89, SC-62	S•D•G•D
Z3	BZV49C5V6	ZETEX	dz	$V_Z(I_{ZT}=5.0 \text{ mA}) = 5.26.0 \text{B}; Z_{ZT}(I_{ZT}=5.0 \text{ mA}) < 40 \text{ Cm};$ $I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
Z4	2SK1079	TOSH	nMOS	V _{DS} = 100 B; I _D = 600 mA; P _D = 500 mBT; R _{DS(on)} < 1.8 Om	SOT-89, SC-62	S•D•G•D
Z4	BZV49C6V2	ZETEX	dz	$V_Z(I_{ZT}=5.0 \text{ mA}) = 5.86.6B; Z_{ZT}(I_{ZT}=5.0 \text{ mA}) < 10 \text{ Cm};$ $I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
Z5	2SK1717	TOSH	nMOS	V _{DS} = 60 B; I _D = 2 A; P _D = 500 mBT; R _{DS(on)} < 0.53 Om	SOT-89, SC-62	G•D•S•D
Z5	BZV49C6V8	ZETEX	dz	$V_Z(I_{ZT}=5.0 \text{ mA}) = 6.47.2 \text{B}; Z_{ZT}(I_{ZT}=5.0 \text{ mA}) < 15 \text{ Cm}; I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
Z6	2SJ238	TOSH	pMOS	V _{DS} = 60B; I _D = 1A; P _D = 500 mBT; R _{DS(on)} = 1.4 Om	SOT-89, SC-62	G•D•S•D
Z6	BZV49C7V5	ZETEX	dz	$V_Z(I_{ZT}=5.0 \text{ mA}) = 7.07.9 \text{B}; Z_{ZT}(I_{ZT}=5.0 \text{ mA}) < 15 \text{ Cm}; I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
Z7	BZV49C8V2	ZETEX	dz	$V_Z(I_{ZT} = 5.0 \text{ mA}) = 7.78.7B$; $Z_{ZT}(I_{ZT} = 5.0 \text{ mA}) < 15 \text{ Cm}$; $I_{ZM} = 250 \text{ mA}$	SOT-89, SC-62	A•K•A•K
Z8	BZV49C9V1	ZETEX	dz	$V_Z(I_{ZT}=5.0 \text{ mA})=8.59.6B; Z_{ZT}(I_{ZT}=5.0 \text{ mA})<15 \text{ Cm}; I_{ZM}=250 \text{ mA}$	SOT-89, SC-62	A•K•A•K



SOT143/343...

Код	Типономинал	Б	Φ	Особенности	Корпус	Ц: 1•2•3•4
18	BFP181T	TELEF	npn	$V_{CB0} = 15 \text{ B}; I_C = 20 \text{ mA}; P_D = 160 \text{ mBT}; h_{21} = 50150; f_T = 8 \Gamma \Gamma I_L$	SOT143, TO253	C•E•B•E
67	BFP67	TELEF	npn	$V_{CB0} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} = 65150; $ $f_T = 7.5 \Pi T_U$	SOT143, TO253	C•E•B•E
77	MA4CS101E	M/A	shd x2	V _B =70 B; I _E <15 мА; V _E (I _E =15 мА)<1 B; C _D <2 пФ	SOT143, TO253	K2 • K1 • A1 • A2
87	MA4CS102E	M/A	shd x2	$V_R = 8 \text{ B}; I_F < 30 \text{ mA}; V_F (I_F = 10 \text{ mA}) < 500 \text{ mB}; C_D < 1 \text{ n}\Phi$	SOT143, TO253	K2 • K1 • A1 • A2
822	S822T	VISH	npn	$V_{CB0} = 12 \text{ B; } I_C = 8 \text{ mA; } P_D = 30 \text{ mBT; } h_{21} = 40150; $ $f_T = 5.2 \text{ TT u}$	SOT143, TO253	C•E•B•E
01	MRF9011LT1	MOT	npn	$V_{CB0} = 25 \text{ B; } I_C = 30 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} = 30200; $ $f_T = 3800 \text{ MF }_U$	SOT143, TO253	C•E•B•E
02	MRF5711LT1	MOT	npn	$V_{CB0} = 20 \text{ B; } I_C = 80 \text{ mA; } P_D = 580 \text{ mBT; } h_{21} = 50300; $ $f_T = 8000 \text{ MFu}$	SOT143, TO253	C•E•B•E
04	MRF4427	MOT	npn	$V_{CB0} = 40 \text{ B; } I_C = 400 \text{ mA; } P_D = 220 \text{ mBr; } h_{21} = 10200; $ $f_T = 1600 \text{ MF }_H$	SOT143, TO253	C•E•B•E
04	MRF5211LT1	MOT	pnp	$V_{CB0} = 20 \text{ B; } I_C = 70 \text{ mA; } P_D = 333 \text{ mBT; } h_{21} = 25125; $ $f_T = 4200 \text{ MF } \mu$	SOT143, TO253	C•E•B•E
05	MRF9331LT1	MOT	npn	$V_{CB0} = 15 \text{ B; } I_C = 2 \text{ mA; } P_D = 50 \text{ mBT; } h_{21} = 30200; \\ f_T = 5000 \text{ MF u}$	SOT143, TO253	C•E•B•E
05F	TSDF1205R	TELEF	npn	$V_{CB0} = 9B_1 I_C = 12 \text{ mA}; P_D = 40 \text{ mBT}; h_{21} = 50250; f_T = 12 \Gamma \Gamma \mu$	SOT143R	C•E•B•E
11	MRF9511ALT1	MOT	npn	V_{CBD} = 20 B; I_C = 100 mA; P_D = 322 mBr; h_{21} = 75150; f_T = 8000 MFu	SOT143, TO253	C•E•B•E
17	BAS125-07	SIEM	shd x2	V_R <25B; I_F <100 mA; V_F (I_F =35 mA)<0.9B; I_R <1.0 mrA; C_D <1.1 n Φ	SOT143, TO253	K1 • K2 • A2 • A1
17s	BAS125-07	INF	shd x2	V_B < 25B; I_F < 100 mA; V_F (I_F = 35 mA) < 0.9 B; I_R < 1.0 mrA; C_D < 1.1 n Φ	SOT143, TO253	K1 • K2 • A2 • A1
17s	BAS125-07W	INF	shd x2	V_B <25B; I_F <100 mA; V_F (I_F =35 mA)<0.9 B; I_R <1.0 mrA; C_D <1.1 n Φ	SOT343, SC82A	K1 • K2 • A2 • A1
18	MRF9331LT1	MOT	npn	$V_{CB0} = 15 \text{ B; } I_C = 2 \text{ mA; } P_D = 50 \text{ mBr; } h_{21} = 30200; $ $f_T = 3500 \text{ MF }_H$	SOT143, TO253	C•E•B•E
18	MRF9411BLT1	MOT	npn	$V_{CB0} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D = 250 \text{ mBT; } h_{21} = 100200; \\ f_T = 8000 \text{ mF } u$	SOT143, TO253	C•E•B•E
18	MRF9411BLT3	MOT	npn	$V_{CB0} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D = 250 \text{ mBT; } h_{21} = 100200; \\ f_T = 8000 \text{ MFu}$	SOT143, TO253	C•E•B•E
1Jp	BCV61A	PHIL	npn x2	$V_{CB0} = 30 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBr; } h_{21} = 110220; $ $f_T > 100 \text{ MFu}$	SOT143, TO253	B1, B2, C2 • C1 • E1 • E2
1Jp	BCV61A	PHIL	npn x2	$V_{CB0} = 30 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBr; } h_{21} = 110220; $ $f_T > 100 \text{ MFu}$	SOT143, TO253	B1, B2, C2 • C1 • E1 • E2
1JS	BCV61A	INF	npn x2	$V_{CB0} = 30 \text{ B; } I_C = 100 \text{ mA; } P_0 = 250 \text{ mBr; } h_{21} = 110220; $ $f_T > 100 \text{ MFu}$	SOT143, TO253	B1, B2, C2 • C1 • E1 • E2
1Js	BCV61A	INF	npn x2	$V_{CB0} = 30 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBr; } h_{21} = 110220; $ $f_T = 250 \text{ MF } \mu$	SOT143, TO253	C1, B1, B2 • C2 • E2 • E1
1Кр	BCV61B	PHIL	npn x2	$V_{CB0} = 30 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBr; } h_{21} = 200450; $ $f_T > 100 \text{ MFu}$	SOT143, TO253	B1, B2, C2 • C1 • E1 • E2
1Ks	BCV61B	INF	npn x2	$V_{CB_0} = 30 \text{ B; } I_C = 100 \text{ mA; } P_0 = 300 \text{ mBr; } h_{21} = 200450; $ $f_T = 250 \text{ MFu}$	SOT143, TO253	C1, B1, B2 • C2 • E2 • E1
1Lp	BCV61C	PHIL	npn x2	$V_{CB0} = 30 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBr; } h_{21} = 420800; $ $f_T > 100 \text{ MFu}$	SOT143, TO253	B1, B2, C2 • C1 • E1 • E2
1Ls	BCV61C	INF	npn x2	$V_{CB0} = 30 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} = 420 800; $ $f_T = 250 \text{ MFu}$	SOT143, TO253	C1, B1, B2 • C2 • E2 • E1
1Мр	BCV61	PHIL	npn x2	$V_{CB0} = 30 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBr; } h_{21} = 110800; $ $f_T > 100 \text{ MFu}$	SOT143, TO253	B1, B2, C2 • C1 • E1 • E2
20	MRF5811LT1	MOT	npn	$V_{CB0} = 36 \text{ B; } I_C = 200 \text{ mA; } P_D = 710 \text{ mBr; } h_{21} = 50200; \\ f_T = 5 \Gamma \Gamma \mu$	SOT143, TO253	C•E•E•B

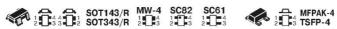
Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1 • 2 • 3 • 4
20F	TSDF1220R	TELEF	npn	$V_{CB0} = 9 \text{ B}; I_C = 40 \text{ mA}; P_D = 200 \text{ mB}\tau; h_{21} = 50150; f_T = 12 \Gamma \Gamma_U$	SOT143R	C•E•B•E
28	BFP280T	TELEF	npn	$V_{CB0} = 15B$; $I_C = 10$ mA; $P_D = 80$ mB τ ; $h_{21} = 50150$; $f_T = 7\Gamma\Gamma q$	SOT143, TO253	C•E•B•E
305	AT30511	HP	npn	$V_{CB0} = 11 \text{ B}; I_C = 8 \text{ mA}; P_D = 100 \text{ mB} \text{ T}; h_{21} = 70300; f_T = 10 \Gamma \Gamma \text{ U}$	SOT143, TO253	B•E•C•E
310	AT31011	HP	npn	$V_{CB0} = 11B$; $I_C = 16 \text{ mA}$; $P_D = 150 \text{ mBT}$; $h_{21} = 70300$; $f_T = 10 \Gamma \Gamma I_L$	SOT143, TO253	B•E•C•E
320	AT32011	HP	npn	$V_{CB0} = 11B$; $I_C = 32 \text{ mA}$; $P_D = 200 \text{ mBT}$; $h_{21} = 70300$; $f_T = 10 \Gamma \Gamma \mu$	SOT143, TO253	B•E•C•E
ЗЈр	BCV62A	PHIL	рпр х2	$V_{CB0} = 30 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} = 125250; f_T > 100 \text{ MFu}$	SOT143, TO253	B1, B2, C2 • C1 • E1 • E2
3Js	BCV62A	INF	pnp x2	$V_{CB0} = 30 \text{ B}; I_C = 100 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} = 125220; f_T = 250 \text{ MFu}$	SOT143, TO253	C1, B1, B2 • C2 • E2 • E1
ЗКр	BCV62B	PHIL	pnp x2	V_{CB0} = 30 B; I_C = 100 mA; P_D = 250 mBT; h_{21} = 220475; f_T > 100 MFu	SOT143, TO253	B1, B2, C2 • C1 • E1 • E2
3Ks	BCV62B	INF	pnp x2	$V_{CB0} = 30 \text{ B}; I_C = 100 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} = 220475; f_T = 250 \text{ MFu}$	SOT143, TO253	C1, B1, B2 • C2 • E2 • E1
3Lp	BCV62C	PHIL	pnp x2	$V_{CB0} = 30 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} = 420800; f_T > 100 \text{ MFu}$	SOT143, TO253	B1, B2, C2 • C1 • E1 • E2
3Ls	BCV62C	INF	pnp x2	$V_{CB0} = 30 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} = 420800; $ $I_T = 0.250 \text{ MF } I_L$	SOT143, TO253	C1, B1, B2 • C2 • E2 • E1
ЗМр	BCV62	PHIL	pnp x2	$V_{CB0} = 30 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} = 100800; f_7 > 100 \text{ MFu}$	SOT143, TO253	B1, B2, C2 • C1 • E1 • E2
3Ms	BCV62	INF	pnp x2	$V_{CB0} = 30 \text{ B}; I_C = 100 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} = 100800; f_7 > 100 \text{ MFu}$	SOT143, TO253	B1, B2, C2 • C1 • E1 E2
3RP	3SK184P	PAN	dnMESFET	$V_{DS} = 13 \text{ B}; I_D = 50 \text{ mA}; P_D = 200 \text{ mB}_T; g_F > 18 \text{ mCm}; I_{DSS} = 8.517 \text{ mA}$	SOT143, TO253	S•D•G2•G1
3RQ	3SK184Q	PAN	dnMESFET	$V_{OS} = 13 \text{ B; } I_{O} = 50 \text{ mA; } P_{O} = 200 \text{ mBT; } g_{F} > 18 \text{ mCm; } I_{OSS} = 1521 \text{ mA}$	SOT143, TO253	S•D•G2•G1
3RR	3SK184R	PAN	dnMESFET	$V_{DS} = 13 \text{ B}; I_D = 50 \text{ mA}; P_D = 200 \text{ mBT}; g_F > 18 \text{ mCm}; I_{DSS} = 1930 \text{ mA}$	SOT143, TO253	S•D•G2•G1
3RS	3SK184S	PAN	dnMESFET	$V_{DS} = 13 \text{ B}; I_D = 50 \text{ mA}; P_D = 200 \text{ mB}\tau; g_F > 18 \text{ mCm}; I_{DSS} = 2535 \text{ mA}$	SOT143, TO253	S•D•G2•G1
414	AT41411	HP	npn	V_{CB0} = 20 B; I_C = 50 mA; P_D = 225 mBr; h_{21} = 30270; f_T = 7000 MF $_{\rm LL}$	SOT143, TO253	C•E•B•E
47s	BAS4007	SIEM	shd x2	$V_R < 40 \text{ B}$; $I_F < 120 \text{ mA}$; $V_F (I_F = 40 \text{ mA}) < 1.0 \text{ B}$; $I_R < 1.0 \text{ mkA}$; $C_0 < 5.0 \text{ n}$	SOT143, TO253	K1 • K2 • A2 • A1
47s	BAS40-07	INF	shd x2	$V_R < 40 \text{ B}; I_F < 120 \text{ mA}; V_F (I_F = 40 \text{ mA}) < 1 \text{ B}; I_R < 1.0 \text{ mkA}; $ $C_D < 5 \text{ n}\Phi$	SOT143, TO253	K1 • K2 • A2 • A1
47s	BAS40-07W	INF	shd x2	$V_R < 40 \text{ B}; I_F < 120 \text{ mA}; V_F (I_F = 40 \text{ mA}) < 1 \text{ B}; I_R < 1.0 \text{ mkA}; $ $C_D < 5 \text{ n}\Phi$	SOT343, SC82A	K1 • K2 • A2 • A1
57	BAT1707	SIEM	shd x2	$V_R \le 4B$; $I_F \le 130$ mA; $V_F (I_F = 10$ mA) ≤ 0.6 B; $I_R \le 0.25$ mkA; $C_D \le 0.75$ π Φ	SOT143, TO253	K1 • K2 • A2 • A1
57s	BAT17-07	INF	shd x2	$V_R < 4B$; $I_F < 130$ mA; $V_F (I_F = 10$ mA) < 0.6 B; $I_R < 0.25$ mkA; $C_0 < 1$ n Φ	SOT143, TO253	K1 • K2 • A2 • A1
60	BAR60	SIEM	pin x3	V_B < 100 B; I_F < 140 mA; V_F (I_F = 100 mA) < 1.25 B; I_B < 0.1 mkA; C_D < 0.2 n Φ	SOT143, TO253	K1, K2, A3 • K3 • A1 • A2
61	BAR61	SIEM	pin x3	$V_R \le 100 \text{ B; } I_F \le 140 \text{ mA; } V_F (I_F = 100 \text{ mA}) \le 1.25 \text{ B; } I_R \le 0.1 \text{ mKA; } C_D \le 0.2 \text{ n} \Phi$	SOT143, TO253	K2, K3 • A1 • K1, A2 • A3
62	BAT62	SIEM	shd x2	$V_R < 40 \text{ B}; I_F < 20 \text{ mA}; V_F (I_F = 2 \text{ mA}) < 1 \text{ B}; I_R < 10 \text{ mKA}; C_D < 0.6 \text{ m}$	SOT143, TO253	A1 • K2 • A2 • K1
62s	BAT62	INF	shd x2	V_R < 40 B; I_F < 20 mA; V_F (I_F = 2 mA) < 1 B; I_R < 10 mkA; C_D < 0.6 n Φ	SOT143, TO253	A1 • K2 • A2 • K1
52s	BAT62-07W	INF	shd x2	$V_R < 40 \text{ B; } I_F < 20 \text{ mA; } V_F (I_F = 2 \text{ mA}) < 1 \text{ B; } I_R < 10 \text{ mkA; } C_D < 0.6 \text{ n} \Phi$	SOT343, SC82A	K1 • K2 • A2 • A1
63	BAT63	SIEM	shd x2	$V_R \le 3B$; $I_F \le 100$ mA; $V_F (I_F = 1$ mA) $\le 0.3B$; $I_R \le 0.01$ mkA; $C_B \le 0.85$ n Φ	SOT143, TO253	A1 • K2 • A2 • K1
67R	BFP67R	TELEF	npn	V_{CBQ} = 20B; I_C = 50 mA; P_D = 200 mBT; h_{21} = 65150; f_T = 7.5 ГГц	SOT143R	C•E•B•E





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4
67s	BAT64-07	INF	shd x2	V_R <40B; I_F <250 mA; V_F (I_F =100 mA)<0.75B; I_R <2.0 mKA; C_D <6 $\pi\Phi$	SOT143, TO253	K1 • K2 • A2 • A1
67s	BAT64-07W	INF	shd x2	V_R < 40 B; I_F < 250 mA; V_F (I_F = 100 mA) < 0.75 B; I_R < 2 mkA; C_D < 6 n Φ	SOT343, SC82A	K1 • K2 • A2 • A1
77p	BAS7007	PHIL	shd x2	$V_R < 70B$; $I_F < 70 \text{ mA}$; $V_F (I_F = 1 \text{ mA}) < 410 \text{ mB}$; $C_D < 2 \text{ n}\Phi$	SOT143, TO253	K1 • K2 • A2 • A1
77s	BAS7007	SIEM	shd x2	$V_R < 70B$; $I_F < 70$ mA; $V_F (I_F = 15$ mA) < 1.0 B; $I_R < 0.1$ mkA; $C_D < 2.0$ n Φ	SOT143, TO253	K1 • K2 • A2 • A1
77s	BAS70-07	INF	shd x2	V_B < 70 B; I_F < 70 mA; V_F (I_F = 15 mA) < 1.0 B; I_B < 0.1 mkA; C_D < 2.0 n Φ	SOT143, TO253	K1 • K2 • A2 • A1
77s	BAS70-07W	INF	shd x2	$V_R < 70B$; $I_F < 70$ mA; $V_F (I_F = 15$ mA) < 1.0 B; $I_R < 0.1$ mkA; $C_D < 2.0$ n Φ	SOT343, SC82A	K1 • K2 • A2 • A1
82P	BFP182T	TELEF	npn	$V_{CBD} = 15 \text{ B}; I_C = 35 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} = 50150; f_T = 7.5 \Gamma \Gamma_U$	SOT143, TO253	C•E•B•E
8372	MRF8372	MOT	npn	V _{CB0} = 36 B; I _C = 200 mA; P _D = 1880 mBT; h ₂₁ = 30200	SOT143, TO253	C•E•B•E
83P	BFP183T	TELEF	npn	$V_{CB0} = 15 \text{ B}; I_C = 65 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} = 50150; f_T = 8 \Gamma \Gamma \mu$	SOT143, TO253	C•E•B•E
87s	BAT68-07	INF	shd x2	$V_{\rm R}$ < 8 B; $I_{\rm F}$ < 130 mA; $V_{\rm F}$ ($I_{\rm F}$ = 10 mA) < 0.5 B; $I_{\rm R}$ < 0.1 mkA; $C_{\rm D}$ < 1.0 n Φ	SOT143, TO253	K1 • K2 • A2 • A1
87s	BAT68-07W	INF	shd x2	$V_B \le 8 \text{ B; } I_F \le 130 \text{ mA; } V_F (I_F = 10 \text{ mA}) \le 0.5 \text{ B; } I_R \le 0.1 \text{ mkA; } C_D \le 1.0 \text{ n} \Phi$	SOT343, SC82A	K1 • K2 • A2 • A1
8ALx	STM811L	STM	mrc	V _{TB} =4.63 B; V _{DO} =1.25.5B; I _{CC} <15 MKA	SOT143, TO253	VSS • RES • MR • VCC
8AMx	STM811M	STM	mrc	V _{тB} =4.38 B; V _{DD} =1.25.5 B; I _{CC} <15 мкА	SOT143, TO253	VSS • RES • MR • VCC
8ANx	STM811T	STM	mrc	V _{TB} = 3.08 B; V _{DD} = 1.25.5B; I _{CC} < 15 mkA	SOT143, TO253	VSS • RES • MR • VCC
8APx	STM811S	STM	mrc	V _{тв} =2.93 B; V ₀₀ =1.25.5B; I _{сс} <15мкА	SOT143, TO253	VSS • RES • MR • VCC
8AQx	STM811R	STM	mrc	V _{тв} = 2.63 B; V _{DD} = 1.25.5B; I _{CC} < 15 мкА	SOT143, TO253	VSS • RES • MR • VCC
8ARx	STM812L	STM	mrc	V _{TR} =4.63 B; V _{DD} =1.25.5B; I _{CC} <15 MKA		VSS • RES • MR • VCC
8ASx	STM812M	STM	mrc	V _{TR} =4.38 B; V _{DD} =1.25.5B; I _{CC} <15mkA		VSS • RES • MR • VCC
8ATx	STM812T	STM	mrc	V _{TR} =3.08 B; V _{DD} =1.25.5B; I _{CC} <15mkA		VSS • RES • MR • VCC
8AUx	STM812S	STM	mrc	V _{TR} =2.93 B; V _{DD} =1.25.5B; I _{CC} <15 MKA		VSS • RES • MR • VCC
8AVx	STM812B	STM	mrc	V _{TR} =2.63 B; V _{DD} =1.25.5 B; I _{CC} <15 MKA		VSS • RES • MR • VCC
92V	BFP92A	TELEF	1	V _{CR0} =20B; I _C =30MA; P _D =200MBT; h ₂₁ =50150;	SOT 143, TO253	
97p	BCV65	PHIL		f _T =6ГГц		C2•B1.B2•C1•E1.
	TOTAL CO.		n(2)	V _{CB0} = 30 B; I _C = 100 mA; P _D = 250 mBr; h ₂₁ = 75800		E2
98p	BCV65B	PHIL	n(2)	$V_{CB0} = 30 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBr; } h_{21} = 200475$		C2 • B1, B2 • C1 • E1, E2
A	MRF947T3	MOT	npn	V_{CBD} = 20 B; I_C = 50 mA; P_D = 188 mBT; h_{21} > 50; f_T = 8000 M Γ_{II}	SOT143, TO253	
A03	VAM-3	MC	amp	V _{CC} = 4.7B; I _{CC} = 35 мА; f _P = 02 ГГц; GAIN = 9.5 дБ		VCC, RF-OUT • GND • RF-IN • GND
A06	VAM-6	MC	amp	V _{CC} = 3.3 B; I _{CC} = 16 мA; f _P = 02 ГГц; GAIN = 10 дБ		VCC, RF-OUT • GND • RF-IN • GND
A07	VAM-7	MC	amp	V _{CC} = 3.8 B; I _{CC} = 22 мА; f _P = 02 ГГц; GAIN = 9.8 дБ	SOT143, TO253	VCC, RF-OUT • GND • RF-IN • GND
A1	1SS272	TOSH	di x2	$V_R > 80B$; $I_F < 300$ mA; $V_F (I_F = 100$ mA) < 1.2 B; $I_R < 0.5$ mKA; $1RR < 4$ Hc	SC61, MPAK-4	K1 • K2 • A2 • A1
A1	1SS382	TOSH	di x2	V_R < 80 B; I_F < 300 mA; V_F (I_F = 100 mA) < 1.2 B; I_R < 0.5 mKA; $1RR$ < 4 Hc	SC82, USQ	A1 • A2 • K2 • K1
A2	CFY30	SIEM	nFET	GaAs; V _{DS} =5B; I _D =80 mA; P _D =250 mBr; I _{DSS} =1560 mA; g _F =30 mCm	SOT143, TO253	S•D•S•G
A3	1SS306	TOSH	di x2	V_R < 200 B, I_F < 300 mA; V_F (I_F = 100 mA) < 1.2 B; I_{RR} < 60 Hc	SC61, MPAK-4	K1 • K2 • A2 • A1
A 4	1SS319	TOSH	di x2	V_R <40B; I_F <300 mA; V_F (I_F =100 mA)<0.6B; I_R (V_R =40B)<5 mkA	SC61, MPAK-4	K1 • K2 • A2 • A1
A4	1SS383	TOSH	shd x2	$V_R < 40B$; $V_F (I_F = 100 \text{ mA}) < 0.6 \text{ B}$; $I_R (V_R = 40 \text{ B}) < 5 \text{ mkA}$; $C_T < 25 \text{ n}\Phi$	SC82, USQ	A1 • A2 • K2 • K1
A5	1SS384	TOSH	shd x2	$V_R \le 15B$; $V_F (I_F = 100 \text{ mA}) \le 0.5 B$; $I_R (V_R = 10 \text{ B}) \le 20 \text{ mrA}$; $C_T \le 40 \text{ n}\Phi$	SC82, USQ	A1 • A2 • K2 • K1

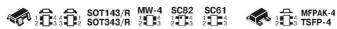
Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1 • 2 • 3 • 4
A5	1SS391	TOSH	shd x2	V _B < 10 B; V _F (I _F = 100 мA) < 0.5 B; I _B (V _B = 10 B) < 20 мкА; С _т < 20 пФ	SC61, MPAK-4	K1 • K2 • A2 • A1
A5	HSMS2805	HP	shd x2	$V_{BR} > 70 \text{ B; } V_F (I_F = 15 \text{ mA}) < 1.0 \text{ B; } I_R (V_R = 50 \text{ B}) < 200 \text{ mA; } C_D < 2.0 \text{ n}\Phi; R_D = 35 \text{ Om}$	SOT143, TO253	K1 • K2 • A2 • A1
A51	BRY62	PHIL	pnp/npn	V_{CB0} =70B; I_C =175 MA; P_D =250 MBT; h_{21NPN} >50; h_{21PNP} >3	SOT143, TO253	AG • A • C • CG
A6	1SS399	TOSH	di x2	V _R <400 B; I _F <100 mA; V _F (I _F = 100 mA)<1.3 B; I _R <1.0 mkA	SC61, MPAK-4	K1 • K2 • A2 • A1
A61	BAS28	CSI	fid x2	I_F < 250 mA; V_{BR} > 75 B; V_F (I_F = 10 mA) < 0.855 B; I_R < 1000 nA; t_{RR} < 6.0 nc; C_D < 2.0 n Φ	SOT143, TO253	A1 • A2 • K2 • K1
A7	1SS402	TOSH	shd x2	$V_R > 20 \text{ B}; V_F (I_F = 50 \text{ mA}) < 0.55 \text{ B}; I_R (V_R = 20 \text{ B}) < 0.5 \text{ mKA}; $ $C_T < 5 \text{ n}\Phi$	SC82, USQ	A1 • A2 • K2 • K1
A7	HSMS2807	HP	shd x4	$V_{BR} > 70 \text{ B; } V_F (I_F = 15 \text{ mA}) < 1.0 \text{ B; } I_R (V_R = 50 \text{ B}) < 200 \text{ HA; } C_0 < 2.0 \text{ n}\Phi; R_0 = 35 \text{ Om}$	SOT143, TO253	K1, A4 • K4, A3 • K3, A2 • K2, A1
A8	HSMS2808	HP	shd x4	$V_{BR} > 70 \text{ B; } V_F (I_F = 15 \text{ mA}) < 1.0 \text{ B; } I_R (V_R = 50 \text{ B}) < 200 \text{ HA; } C_D < 2.0 \text{ n}\Phi; R_D = 35 \text{ OM}$	SOT143, TO253	K1, K4 • A4, K3 • A3, A2 • K2, A1
AAB	MAX6711LXS	MAX	mrc	V _{тв} = 4.63B; V _{DD} = 1.25.5B; I _{CC} < 60 мкА	SOT343, SC82A	GND • RES • MR • VCC
AAC	MAX6711MXS	MAX	mrc	V _{TR} = 4.38B; V _{DD} = 1.25.5B; I _{CC} < 60 mkA	SOT343, SC82A	GND • RES • MR • VCC
AAD	MAX6711TXS	MAX	mrc	V _{TB} = 3.08B; V _{DD} = 1.25.5B; I _{CC} < 60 MKA	SOT343, SC82A	GND • RES • MR • VCC
AAE	MAX6711SXS	MAX	mrc	V _{TB} = 2.93B; V _{DD} = 1.25.5B; I _{CC} < 60 mKA	SOT343, SC82A	GND • RES • MR • VCC
AAF	MAX6711RXS	MAX	mrc	V _{TR} = 2.63B; V _{DD} = 1.25.5B; I _{CC} < 60 мкА	SOT343, SC82A	GND • RES • MR • VCC
AAG	MAX6711ZXS	MAX	mrc	V _{тв} = 2.32B; V _{DD} = 1.25.5B; I _{CC} < 60 мкА	SOT343, SC82A	GND • RES • MR • VCC
AAH	MAX6712LXS	MAX	mrc	V _{TB} = 4.63B; V _{DD} = 1.25.5B; I _{CC} < 60 мкА	SOT343, SC82A	GND • RES • MR • VCC
AAI	MAX6712MXS	MAX	mrc	V _{TR} = 4.38B; V _{DD} = 1.25.5B; I _{CC} < 60 мкА	SOT343, SC82A	GND • RES • MR • VCC
AAJ	MAX6712TXS	MAX	mrc	V _{TR} = 3.08B; V _{DD} = 1.25.5B; I _{CC} < 60 MKA	SOT343, SC82A	GND • RES • MR • VCC
AAK	MAX6712SXS	MAX	mrc	V _{TR} = 2.93B; V _{DD} = 1.25.5B; I _{CC} < 60 mkA	SOT343, SC82A	GND • RES • MR • VCC
AAL	MAX6712RXS	MAX	mrc	V _{TB} = 2.63B; V _{DD} = 1.25.5B; I _{CC} < 60 мкА	SOT343, SC82A	GND • RES • MR • VCC
AAM	MAX6712ZXS	MAX	mrc	V _{TB} = 2.32B; V _{DD} = 1.25.5B; I _{CC} < 60 mkA	SOT343, SC82A	GND • RES • MR • VCC
AAN	MAX6713LXS	MAX	mrc	V _{TB} = 4.63B; V _{DD} = 1.25.5B; I _{CC} < 60 MKA	SOT343, SC82A	GND • RES • MR • VCC
AAO	MAX6713MXS	MAX	mrc	V _{TR} = 4.38B; V _{DD} = 1.25.5B; I _{CC} < 60 mKA	SOT343, SC82A	GND • RES • MR • VCC
AAP	MAX6713TXS	MAX	mrc	V _{TR} = 3.08B; V _{DD} = 1.25.5B; I _{CC} < 60 mkA	SOT343, SC82A	GND • RES • MR • VCC
AAQ	MAX6713SXS	MAX	mrc	V _{TR} = 2.93B; V _{DD} = 1.25.5B; I _{CC} < 60 мкА	SOT343, SC82A	GND • RES • MR • VCC
AAR	MAX6713RXS	MAX	mrc	V _{TR} = 2.63B; V _{DD} = 1.25.5B; I _{CC} < 60 mkA	SOT343, SC82A	GND • RES • MR • VCC
AAS	MAX6713ZXS	MAX	mrc	V _{TR} = 2.32B; V _{DD} = 1.25.5B; I _{CC} < 60 mkA	SOT343, SC82A	GND • RES • MR • VCC
AAT	MAX6384XS16D3	MAX	mrc	V _{TR} = 1.58B; V _{DD} = 15.5B; I _{CC} ≤ 13 mKA	SOT343, SC82A	GND • RES • MR • VCC
AAU	MAX6385XS26D3	MAX	mrc	V _{TR} = 2.63B; V _{DD} = 15.5B; I _{CC} < 13 mKA	SOT343, SC82A	GND • RES • MR • VCC
AAV	MAX6386XS17D3	MAX	mrc	V _{TR} = 1.67B; V _{DD} = 15.5B; I _{CC} < 13 mKA		GND • RES • MR • VCC
AAW	MAX6387XS31D3	MAX	mrc	$V_{TR} = 3.08 \text{ B}; V_{DD} = 15.5 \text{ B}; I_{CC} \le 13 \text{ MKA}$	SOT343, SC82A	GND • RES • RES IN • VCC
AAX	MAX6388XS29D1	MAX	mrc	$V_{TR} = 2.93 B; V_{DD} = 15.5 B; I_{CC} \le 13 \text{ MKA}$	SOT343, SC82A	GND ◆ RES ◆ RES IN ◆ VCC
AAY	MAX6389XS22D3	MAX	mrc	V _{TR} = 2.2 B; V _{DD} = 15.5 B; I _{CC} < 13 mKA	SOT343, SC82A	GND • RES • RES IN • VCC
AAZ	MAX6390XS26D4	MAX	mrc	V _{TR} = 2.63B; V _{DD} = 15.5B; I _{CC} < 13 mKA	SOT343, SC82A	GND • RES • MR • VCC
ABA	MAX6384XS46D2	MAX	mrc	V _{TR} = 4.63B; V _{DD} = 15.5B; I _{CC} < 13 mKA	SOT343, SC82A	GND • RES • MR • VCC
ACs	BFP620F	SIEM	npn	V_{CB0} =7.5B; I_C =80 mA; P_D =185 mBT; h_{21} =110270; f_T =65 $\Gamma \Gamma_{II}$	TSFP-4	B•E•C•E
AE	1SS383T1G	ON	shd x2	$V_{\rm R}\!<\!40{\rm B}; V_{\rm F}(I_{\rm F}\!=\!100{\rm mA})\!<\!0.6{\rm B}; I_{\rm R}(V_{\rm R}\!=\!40{\rm B})\!<\!5{\rm mkA}; C_{\rm T}\!<\!25{\rm n}\Phi$	SC82, USQ	A1 • A2 • K2 • K1
ALs	BFP405	SIEM	npn	V_{CB0} = 15B; I_C = 12 mA; P_0 = 55 mB τ ; h_{21} = 50150; f_T > 20 $\Gamma\Gamma_U$	SOT343, SC82A	B•E•C•E
AMs	BFP420	SIEM	npn	V_{CB0} = 15B; I_C =35 mA; P_D = 160 mBT; h_{21} = 50150; f_T > 20 fF $_U$	SOT343, SC82A	B•E•C•E
ANs	BFP450	SIEM	npn	V_{CB0} = 15B; I_C = 10 mA; P_D = 450 mBT; h_{21} = 50150; f_T > 15 $\Gamma\Gamma_{IJ}$	SOT343, SC82A	B•E•C•E





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4
APs	BFP520	INF	npn	$V_{CB0} = 10 \text{ B}; I_C = 40 \text{ mA}; P_D = 100 \text{ mB} \text{ T}; h_{21} = 70200; f_T = 45 \Gamma \Gamma \mu$	SOT343, SC82A	B•E•C•E
ATs	BFP540	SIEM	npn	$V_{CB0} = 14 \text{ B; } I_C = 80 \text{ mA; } P_D = 250 \text{ mBT; } h_{21} = 50200; $ $f_T = 30 \Gamma\Gamma\text{U}$	SOT343, SC82A	B•E•C•E
B08	SST6908	SIL	nFET	$V_{DS} = 30 \text{ B}; P_D = 350 \text{ mBT}; I_{DSS} > 2 \text{ mA}; g_F = 3 \text{ mCm}$	SOT143, TO253	G • PRDI • S • D
B09	SST6909	SIL	nFET	$V_{DS} = 30 \text{ B}; P_D = 350 \text{ mBT}; I_{DSS} > 10 \text{ mA}; g_F > 0.4 \text{ mCm}$	SOT143, TO253	G • PRDI • S • D
B10	SST6910	SIL	nFET	$V_{DS} = 30 \text{ B}; P_D = 350 \text{ mBT}; I_{DSS} > 10 \text{ mA}; g_F > 1.2 \text{ mCm}$	SOT143, TO253	G • PRDI • S • D
B 5	HSMS2815	HP	shd x2	$V_{BR} > 20 \text{ B}; V_F (I_F = 35 \text{ mA}) < 1.0 \text{ B}; I_R (V_R = 15 \text{ B}) < 200 \text{ mA}; C_T < 1.2 \text{ n}\Phi; R_D = 15 \text{ OM}$	SOT143, TO253	K1 • K2 • A2 • A1
B7	HSMS2817	HP	shd x4	$V_{BR} > 20B$; $V_F (I_F = 35 \text{ mA}) < 1.0B$; $I_R (V_R = 15B) < 200 \text{ mA}$; $C_0 < 1.2 \text{ n}\Phi$; $R_0 = 150 \text{ m}$	SOT143, TO253	K1, A4 • K4, A3 • K3, A2 • K2, A1
B8	HSMS2818	HP	shd x4	$V_{BR} > 20B$; $V_E(I_E = 35 \text{ mA}) < 1.0 B$; $I_B(V_B = 15 B) < 200 \text{ mA}$; $C_D < 1.2 \text{ n}\Phi$; $R_D = 15 \text{ OM}$	SOT143, TO253	K1, K4 • A4, K3 • A3, A2 • K2, A1
BB	1SV237	TOSH	pin x2	$V_R > 50B$; $I_F < 50 \text{ mA}$; $V_F (I_F = 50 \text{ mA}) = 0.95 B$; $I_R < 0.1 \text{ mKA}$	SC61, MPAK-4	K1 • K2 • A2 • A1
BB	1SV312	TOSH	pin x2	$V_B > 50 \text{ B}; I_F < 50 \text{ mA}; V_F (I_F = 50 \text{ mA}) < 1 \text{ B}; I_R < 0.1 \text{ mKA}$	SC82, USQ	A1 • A2 • K2 • K1
BBs	BAR81	INF	di	V _B <30B; I _F <100 мA; V _F (I _F =100 мA)<1B; I _B <0.02 мкA; C _D <0.6 пФ	SOT143, TO253	K•A•K•A
BBs	BAR81W	INF	di	V_B < 30 B; I_F < 100 мА; V_F (I_F = 100 мА) < 1 B; I_B < 0.02 мкА; C_D < 0.6 пФ	SOT343, SC82A	
BLs	BGA310	INF	amp	I_{CC} =60 мA; G_{MA} =9 дБ (f_T = 1 ГГц)		OUT/BIAS • GND • IN • GND
BLs	BGA420	SIEM	amp	$I_{CC} = 15$ мА; $G_{MA} = 13$ дБ ($f_T = 1.8$ ГГц)		IN • GND • OUT • VD
BMs	BGA312	INF	amp	I_{CC} = 60 мA; G_{MA} = 11 дБ (f_T = 1 ГГц)		OUT/BIAS • GND • IN • GND
BMs	BGA427	INF	amp	$V_{CC} = 25B$; $I_{CC} = 25 \text{ мA}$; $G_{MA} = 18.5 \text{дБ} (f_T = 1.8 \Gamma \Gamma_U)$	SOT343, SC82A	IN • GND • VD • OUT
BNs	BGA318	INF	amp	I_{CC} =60 мA; G_{MA} =16 дБ (f_T =1 ГГц)	SOT143, TO253	OUT/BIAS • GND • IN • GND
BNs	BGA612	INF	amp	$V_{CC} = 2.43$ В; $I_{CC} = 80$ мА; $G_{MA} = 17$ дБ ($f_T = 1$ ГГц)	SOT343, SC82A	IN • GND • CUT • GND
BOs	BGA614	INF	amp	$V_{CC} = 2.43$ В; $I_{CC} = 80$ мА; $G_{MA} = 17$ дБ ($f_T = 1$ ГГц)	SOT343, SC82A	IN • GND • OUT • GND
BPs	BGA616	INF	amp	$V_{CC} = 4.56$ В; $I_{CC} = 80$ мА; $G_{MA} = 17$ дБ ($f_T = 1$ ГГц)	SOT343, SC82A	IN • GND • OUT • GND
BRs	BGA622	INF	amp	V _{CC} = 2.43 B; f _{BD} = 0.56 ГГц)	SOT343, SC82A	IN • GND • OUT • VCC
C5	HSMS2825	HP	shd x2	$V_{BR} > 15 B$; $V_F (I_F = 30 \text{ mA}) < 0.7 B$; $I_B (V_B = 1 B) < 100 \text{ mA}$; $C_0 < 1.0 n\Phi$; $R_0 = 12 \text{ OM}$	SOT143, TO253	K1 •K2 • A2 •A1
C7	HSMS2827	HP	shd x4	$V_{BR} > 15 B_i V_F (I_F = 30 \text{ mA}) < 0.7 B_i I_B (V_B = 1 B) < 100 \text{ mA};$ $C_T < 1.0 \text{ m}\Phi_i R_D = 12 \text{ Om}$	SOT143, TO253	K1, A4 • K4, A3 • K3, A2 • K2, A1
C8	HSMS2828	HP	shd x4	$V_{BR} > 15 B$; $V_F (I_F = 30 \text{ mA}) < 0.7 B$; $I_R (V_R = 1 \text{ B}) < 100 \text{ mA}$; $C_T < 1.0 \text{ n}\Phi$; $R_D = 12 \text{ Om}$	100 to 10	K1, K4 • A4, K3 • A3, A2 • K2, A1
C9	HSMS2829	HP	shd x4	$V_{BR} > 15 B_i V_F (I_F = 30 \text{ mA}) < 0.7 B_i I_B (V_B = 1 B) < 100 \text{ mA};$ $C_T < 1.0 \text{ n}\Phi_i R_D = 12 \text{ OM}$		K1, A2 • A3, K4 • A4, K2 • K3, A1
C95	BCV64	PHIL	рпр х2	V_{CB0} =30 B; I_C =100 mA; P_D =250 mBr; h_{21} =110800; f_T >100 M Γ_{IJ}		B1, C2 • C1 • E1, E2 • B2
C96	BCV64B	PHIL	рпр х2	V_{CB0} = 30 B; I_C = 100 mA; P_D = 250 mBr; h_{21} = 220475; f_T > 100 MF $_{\rm LL}$		B1, C2 • C1 • E1, E2 • B2
D1	SST211	T EMI C	nFET	$V_{DS} = 30 \text{ B}; P_D = 300 \text{ mBT}; I_{DSS} = 420 \text{ mA}; R_{DS(cn)} < 50 \text{ Om}$	100	SUBSTR • S • D • G
D3	SST213	T EMI C	nFET	$V_{DS} = 10 \text{ B}; P_D = 300 \text{ mBT}; I_{DSS} = 420 \text{ mA}; R_{DS(cn)} < 50 \text{ Om}$		
D5	SST215	C	nFET	$V_{DS} = 20 \text{ B}; P_D = 300 \text{ mBT}; I_{DSS} = 420 \text{ mA}; R_{DS(en)} \le 50 \text{ Om}$		
D89	BAT74	STM	shd x2	$V_R < 30B$; $I_F < 200 \text{ mA}$; $V_F (I_F = 1 \text{ mA}) < 320 \text{ mB}$; $C_O < 10 \text{ n}\Phi$; $I_{RR} < 5 \text{ Hz}$		
D95	BCV63	PHIL	npn x2	V_{CB0} = 30 B; I_C = 100 mA; P_D = 250 mBr; h_{21} = 110800; f_T > 100 M Γ_{IJ}	M. Choo. Choo. & Choo. C	B1, C2 • C1 • E1, E2 • B2
D96	BCV63B	PHIL	npn x2	V_{CB0} = 30 B; I_C = 100 mA; P_D = 250 mBr; h_{21} = 200450; f_T > 100 MF $_{\rm L}$		B1, C2 • C1 • E1, E2 • B2
DF_	MAX2611EUS	MAX	amp	V _{CC} =5B; f _P =01100МГц; I _{CC} <40мА		OUT • GND • IN • GND
DG_	MAX2630EUS	MAX	атр	V _{CC} = 2.75.5 B; f _P <900МГц; I _{CC} = 6.6 мА		OUT • GND • IN • VCC
DHAA	MAX2650EUS	MAX	amp	V _{CC} = 4.55.5В; f _P <900МГц; I _{CC} <22мА	SOT143, TO253	OUT • GND • IN • VCC

Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1 • 2 • 3 • 4
Ol	2SC3867	REN	npn	V_{CB0} = 20B; I_C = 50 mA; P_D = 150 mBT; h_{21} = 20200; f_T > 1400 MF $_{II}$	SOT343, SC82A	B∙E•C•n.c.
EC	2SC2732	REN	npn	V_{CB0} =30B; I_C =20mA; P_D =150 mBT; h_{21} >30; f_T >700 M Γ_{II}	SOT343, SC82A	E•B•C•n.c.
El	3SK182	REN	nMOS	V _{DS} = 20 B; I _D = 50 мА; P _D = 150 мВт; P _G > 10 дБ; NF < 6.0 дБ	SOT343, SC82A	S•D•G2•G1
F05	TSDF1205	TELEF	npn	V _{CBO} =9B; I _C =12 mA; P _D =40 mBT; h ₂₁ =50250; f _T =12 ΓΓu,	SOT143, TO253	C•E•B•E
F20	TSDF1220	TELEF	npn	$V_{CB0} = 9 \text{ B}; I_C = 40 \text{ mA}; P_D = 200 \text{ mB}_T; h_{21} = 50150; f_T = 12 \Gamma \Gamma I_L$	SOT143, TO253	C•E•B•E
FAs	BFP81	SIEM	npn	V_{C80} = 25B; I_C = 30 mA; P_D = 280 mBT; h_{21} = 50200; f_T > 5800 MF $_{\rm H}$	SOT143, TO253	C•E•B•E
FB	BFP17	INF	npn	V _{CB0} =12B; I _C =50mA; P _D =280 mB _T	SOT143, TO253	E•C•E•B
FC	BFP29	SIEM	npn	V _{CB0} =15B; I _C =30mA; P _D =280 mB _T	SOT143, TO253	E•C•E•B
FEs	BFP93A	SIEM	npn	$V_{CB0} = 20B$; $I_C = 50 \text{ mA}$; $P_D = 300 \text{ mBT}$; $h_{21} = 50200$; $f_T > 6000 \text{ MFL}$	SOT143, TO253	C•E•B•E
FI	3SK186	REN	nMOS	V _{DS} = 12 B; I _D = 35 мА; P _D = 150 мВт; P _G > 16 дБ; NF < 4.5 дБ	SOT343, SC82A	S•D•G2•G1
G2	CGY50	SIEM	amp	GaAs; V _{CC} = 2.76В; f ₈₀ =0.13ГГц	SOT143, TO253	GND/S • OUT/D • GND/S • IN/G
G5	HSMP3895	HP	pinx2	I_E <1 A; P_D <250 mBτ; V_{BR} >100 B; R_S <2.5 Om; CT<0.30 nΦ	SOT143, TO253	A1 • A2 • K2 • K1
GC	2SC2734	REN	npn	V_{CB0} =20B; I_C =50mA; P_D =150 mBT; h_{21} =20200; f_T >1.4 $\Gamma\Gamma U_L$	SOT343, SC82A	E•B•C•n. c.
GIA	2SC3957A	REN	dnpn	V _{CB0} =40B; I _C =300 mA; P _D =150 mBT; h ₂₁ =2000100000	SOT143, TO253	C • n. c. • B • E
GIB	2SC3957B	REN	dnpn	V _{CB0} =40B; I _C =300 mA; P _D =150 mBT; h ₂₁ =5000100000	SOT143, TO253	C●n. c. ●B●E
HC	2SC2733	REN	npn	V _{GBO} = 30 B; I _C = 50 mA; P _D = 150 mBT; h ₂₁ > 60; f _T > 600 MFu	SOT343, SC82A	E∙B•C•n.c.
HG	CFY77-08	SIEM	nFET	AlGaAs/InGaAs HEMT; V _{DS} = 3.5 B; I _D = 60 мA; P _D = 180 мВт; NF = 0.8 дБ	MW-4	S•D•S•G
НН	CFY77-10	SIEM	nFET	AlGaAs/InGaAs HEMT; V _{DS} = 3.5 B; I _D = 60 мA; P _D = 180 мВт; NF = 1 дБ	MW-4	S•D•S•G
HHs	BBY51-07	INF	varx2	$V_R < 7B$; $I_F < 20$ mA; $I_R < 0.01$ mkA; $C_{1B} = 4.86.0$ n Φ ; $C_{2B}/C4V = 1.552.15$	SOT143, TO253	K1 • K2 • A2 • A1
HI	3SK188	REN	nMOS	V _{DS} =22 B; I _D =35 мA; P _D =150 мВт; P _G >18 дБ; NF<3.2 дБ	SOT343, SC82A	S•D•G2•G1
ID	2SC3127	REN	npn	V_{CB0} = 20B; I_C = 50 mA; P_D = 150 mBT; P_G = 10.5 p_G ; f_T > 3500 MF g	SOT343, SC82A	E•B•C•n. c.
IJ	2SC3374	REN	npn	V_{CB0} = 20B; I_C = 20mA; P_D = 150 mBT; h_{21} = 20200; f_T > 400 MFu	SOT343, SC82A	E•B•C•n. c.
IL	2SC3493	REN	npn	V_{CB0} = 15B; I_C = 20 mA; P_D = 150 mBT; h_{21} = 30200; f_T > 700 MT μ	SOT343, SC82A	E•B•C•n. c.
IP	2SC3793	REN	npn	V_{CB0} = 20B; I_{C} = 50 mA; P_{D} = 150 mBT; h_{21} = 50200; f_{T} > 1400 MFц	SOT343, SC82A	E•B•C•n.c.
IS	2SC3513	REN	npn	V_{CB0} = 15B; I_C = 50 mA; P_D = 150 mBT; h_{21} = 50250; f_T > 4500 MF $_{\rm H}$	SOT343, SC82A	E•B•C•n.c.
П	3SK 162	REN	dnMOS	V _{DS} = 12 B; I _D = 35 мА; P _D = 150 мВт; P _G > 18 дБ; NF < 3.0 дБ	SOT343, SC82A	S•D•G2•G1
IV	2SK668	REN	nFET	GaAs; V_{DS} = 6.0 B; I_D = 100 мА; P_{CH} = 150 мВт; P_G = 10 дБ; NF = 2.5 дБ	SOT343, SC82A	G•S•D•G
V	3SK136	REN	dnMOS	V_{DS} = 20 B; I_0 = 35 мA; P_D = 150 мВт; P_S > 17 дБ; NF < 3.3 дБ	SOT343, SC82A	S•D•G2•G1
W	3SK137	REN	dnMOS	V _{DS} = 15 B; I _D = 35 мА; P _D = 150 мВт; P _G > 10 дБ; NF < 5.0 дБ	SOT343, SC82A	S•D•G2•G1
W	3SK137V	REN	dnMOS	V _{DS} = 15 B; I _D = 35 мA; P _D = 150 мВт; P _G > 20 дБ; NF < 3.0 дБ	SOT343, SC82A	S•D•G2•G1
X	3SK138	REN	dnMOS	V _{DS} = 15 B; I _D = 35 мА; P _D = 150 мВт; P _G > 10 дБ; NF < 5.0 дБ	SOT343, SC82A	S•D•G2•G1





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4
IY	3SK194	REN	nMOS	V_{DS} = 15 B; I_D = 35 мA; P_D = 150 мВт; P_G > 27 дБ; NF < 2.5 дБ	SOT343, SC82A	S•D•G2•G1
IZ	3SK154	REN	dnMOS	V_{DS} = 15 B; I_D = 35 мА; P_D = 150 мВт; P_G > 22 дБ; NF< 3.0 дБ	SOT343, SC82A	S•D•G2•G1
JC	2SC2735	REN	npn	$V_{CB0} = 30 \text{ B; } I_C = 50 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} > 40; \\ f_T > 600 \text{ MFL}_1$	SOT343, SC82A	E • B • C • n. c.
JKs	BF1009	INF	dnMOS	V _{DS} = 12B; I _D = 25 mA; P _D = 200 mBT; g _F = 24 mCm	SOT143, TO253	S•D•G2•G1
JLs	BF1009S	INF	dnMOS	V _{DS} = 12B; I _D = 25 mA; P _D = 200 mBT; g _F = 30 mCm	SOT143, TO253	S•D•G2•G1
JLs	BF1009SR	INF	dnMOS	V _{DS} = 12B; I _D = 25 mA; P _D = 200 mBt; g _F = 30 mCm	SOT143R	D•S•G1•G2
JPs	BAW101	SIEM	di x2	V_R < 300 B; I_F < 250 mA; V_F (I_F = 100 mA) < 1.3 B; I_R < 0.15 mKA; C_D < 6.0 n Φ ; t_{RR} < 1000 Hc	SOT143, TO253	K1 • K2 • A2 • A1
JSs	BAW100	SIEM	di x2	V_{R} <75B; I_{F} <200 mA; V_{F} (I_{F} =150 mA)<1.25B; I_{R} <1.0 mKA; C_{D} <2.0 n Φ ; I_{RR} <6 HC	SOT143, TO253	A1 • A2 • K2 • K1
JTp	BAS28	PHIL	fd x2	$V_B < 75B$; $I_F < 215$ mA; $V_F (I_F = 50$ mA) ≤ 1.0 B; $C_D \le 1.5$ n Φ ; $t_{RR} \le 4$ HC	SOT143, TO253	K1 • K2 • A2 • A1
JTs	BAS28	INF	di x2	$\begin{array}{l} V_{B}\!<\!75B; I_{F}\!<\!200\text{mA}; V_{F}(I_{F}\!=\!50\text{mA})\!<\!1.0B; I_{B}\!<\!0.1\text{mkA}; \\ C_{D}\!<\!2.0\text{n}\Phi; t_{BB}\!<\!4\text{hc} \end{array}$		
JTs	BAS28W	INF	di x2	V_{R} < 75B; I_{F} < 200 mA; V_{F} (I_{F} =50 mA) < 1.0 B; I_{R} < 0.1 mrA; C_{D} < 2.0 n Φ ; t_{RR} < 4 hc	SOT343, SC82A	K1 • K2 • A2 • A1
JXAA	MAX6160EUS	MAX	vref	V _{IN} = 2.712.6 B; I _{CC} < 130 mrA; V _{OUT} = 1.2312.4 B		GND • ADJ • IN • OUT
KAAP	MAX6335US16D3	MAX	mrc	V _{TR} = 1.6B; V _{DD} = 1.25.5B; I _{CC} < 7 мкА		GND • RES • MR • VCC
KAAQ	MAX6335US18D3	MAX	mrc	V _{TR} = 1.8B; V _{DD} = 1.25.5B; I _{CC} < 7 мкА	SOT 143, TO253	GND • RES • MR • VCC
Kaar	MAX6335US22D3	MAX	mrc	V _{TR} =2.2B; V _{DD} =1.25.5B; I _{CC} <7 mkA	SOT143, TO253	GND • RES • MR • VCC
Kaas	MAX6336US16D3	MAX	mrc	V _{TR} = 1.6B; V _{DD} = 1.25.5B; I _{CC} < 7 mKA	SOT143, TO253	GND • RES • MR • VCC
KAAT	MAX6336US18D3	MAX	mrc	V _{TR} = 1.8B; V _{DD} = 1.25.5B; I _{CC} < 7 mKA	SOT143, TO253	GND • RES • MR • VCC
KAAU	MAX6336US20D3	MAX	mrc	V _{TR} =2.0B; V _{DD} =1.25.5B; I _{CC} <7 mKA	SOT143, TO253	GND • RES • MR • VCC
Kaav	MAX6336US22D3	MAX	mrc	V _{TR} =2.2B; V _{DD} =1.25.5B; I _{CC} <7 mrA	SOT143, TO253	GND • RES • MR • VCC
KAAW	MAX6336US23D3	MAX	mrc	V _{TB} =2.3B; V _{DD} =1.25.5B; I _{CC} <7 mKA	SOT143, TO253	GND • RES • MR • VCC
KAAX	MAX6337US16D3	MAX	mrc	V _{TB} = 1.6B; V _{DD} = 1.25.5B; I _{CC} < 7 mKA	SOT143, TO253	GND • RES • MR • VCC
KAAY	MAX6337US18D3	MAX	mrc	V _{TB} = 1.8B; V _{DD} = 1.25.5B; I _{CC} < 7 mKA	SOT143, TO253	GND • RES • MR • VCC
KAAZ	MAX6337US22D3	MAX	mrc	V _{тв} = 2.2B; V _{пр} = 1.25.5B; I _{пр} < 7 мкА	SOT143, TO253	GND • RES • MR • VCC
KABA	MAX6816EUS	MAX	swd	V _{DC} =2.75.5B; I _{DC} < 20мкА	SOT 143, TO253	GND • IN • OUT • VCC
KABP	MAX6335US20D3	MAX	mrc	V _{TB} =2.0B; V _{DD} =1.25.5B; I _{CC} <7 mKA	SOT143, TO253	GND • RES • MR • VCC
KABO	MAX6335US23D3	MAX	mrc	V _{TB} = 2.3B; V _{DD} = 1.25.5B; I _{CC} < 7 mKA	SOT143, TO253	GND • RES • MR • VCC
KABR	MAX6337US20D3	MAX	mrc	V _{тв} =2.0B; V _{рр} =1.25.5B; I _{гс} <7мкА		GND • RES • MR • VCC
KABS	MAX6337US23D3	MAX	mrc	V _{тв} = 2.3B; V _{DD} = 1.25.5B; I _{DC} < 7 мкА	SOT143, TO253	GND • RES • MR • VCC
KABT	MAX6806US46	MAX	vd	V _{TB} =4.6B; V _{DD} =1.25.5B; I _{CC} <80 мкA		RES • MR • VCC • GND
KABU	MAX6806US26	MAX	vd	V _{TB} = 2.6B; V _{DD} = 1.25.5B; I _{CC} < 80 мкА		RES • MR • VCC • GND
KABV	MAX6806US23	MAX	vd	V _{TB} = 2.3B; V _{DD} = 1.25.5B; I _{CC} < 80 mkA		RES • MR • VCC • GND
KABW	MAX6807US46	MAX	vd	V _{TB} = 4.6B; V _{DD} = 1.25.5B; I _{CC} < 80 mKA		RES • MR • VCC • GND
KABX	MAX6807US26	MAX	vd	V _{TB} = 2.6B; V _{DD} = 1.25.5B; I _{CC} < 80 mkA		RES • MR • VCC • GND
KABY	MAX6808US46	MAX	vd	V _{TB} = 4.6B; V _{DD} = 1.25.5B; I _{CC} < 80 mkA		RES • MR • VCC • GND
KABZ	MAX6808US26	MAX	vd	V _{TB} = 2.6B; V _{DD} = 1.25.5B; I _{CC} < 80 mKA		RES • MR • VCC • GND
KACA	MAX6336US25D3	MAX	mrc	V _{TB} =2.5B; V _{DD} =1.25.5B; I _{CC} <7 mKA		GND • RES • MR • VCC
KACB	MAX6337US17D3	MAX	mrc	V _{TR} =2.3B, V _{DD} =1.23B, I _{CC} <7 MKA V _{TR} =1.7B; V _{DD} =1.25.5B; I _{CC} <7 MKA		GND • RES • MR • VCC
KACC	MAX6808US32	MAX	vd	V _{TR} =3.2B; V _{DD} =1.25.5B; I _{CC} <80 mkA		RES • MR • VCC • GND
KACE	MAX6337US16D2	MAX	mrc	V _{TR} = 1.6B; V _{DD} =1.25.5B; I _{CC} <7 MKA		GND • RES • MR • VCC
KACF	MAX6337US10D2	MAX	mrc	V _{TR} =2.4B; V _{DD} =1.25.5B; I _{CC} <7 MKA		GND • RES • MR • VCC
KACH	MAX6803US26D3	MAX	mrc	V _{TR} =2.4B, V _{DD} =1.25.5B; I _{CC} <7 MKA V _{TR} =2.63B; V _{DD} =1.25.5B; I _{CC} <12 MKA		GND • RES • MR • VCC
KACI	MAX6803US29D3					GND • RES • MR • VCC
KACJ	MAX6803US31D3	MAX	mrc	V _{TR} =2.93 B; V _{DO} =1.25.5B; I _{CC} <12 m/A		GND • RES • MR • VCC
				V _{TR} =3.08 B; V _{DO} =1.25.5B; I _{CC} <12мкА		
KACK	MAX6803US44D3	MAX	mrc	V _{TR} =4.38 B; V _{DO} =1.25.5B; I _{CC} <12 mrA		GND • RES • MR • VCC
KACL	MAX6803US46D3	MAX	mrc	V _{TR} =4.63 B; V _{DO} =1.25.5B; I _{CC} <12 mKA		GND • RES • MR • VCC
KACN	MAX6804US26D3	MAX	mrc	V _{TR} = 2.63 B; V _{DD} = 1.25.5B; I _{CC} < 12 мкА	SOT 143, TO253	GND • RES • MR • VCC



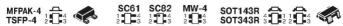


Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1 • 2 • 3 • 4
KACO	MAX6804US29D2	MAX	mrc	V _{тв} = 2.93 B; V _{рв} = 1.25.5 B; I _{сс} < 12 мкА	SOT143, TO253	GND • RES • MR • VCC
KACP	MAX6804US29D3	MAX	mrc	V _{тв} = 2.93B; V _{pp} = 1.25.5B; I _{cc} < 12 мкА	SOT143, TO253	GND • RES • MR • VC
KACQ	MAX6804US31D3	MAX	mrc	V _{TR} = 3.08 B; V _{DD} = 1.25.5 B; I _{CC} < 12 MKA		GND • RES • MR • VC
KACR	MAX6804US44D3	MAX	mrc	V _{TR} =4.38B; V _{DD} =1.25.5B; I _{CC} <12 mKA	SOT143 TO253	GND • RES • MR • VCC
KACS	MAX6804US46D3	MAX	mrc	V _{TR} = 4.63B; V _{DD} = 1.25.5B; I _{CC} < 12 MKA		GND • RES • MR • VC
KACT	MAX6805US26D3	MAX	mrc	V _{тв} = 2.63B; V _{DD} = 1.25.5B; I _{CC} < 12 мкА		GND • RES • MR • VC
KACU	MAX6805US29D3	MAX	mrc	V _{тв} = 2.93B; V _{DD} = 1.25.5B; I _{CC} < 12 мкА		GND • RES • MR • VC
KACV	MAX6805US31D3	MAX	mrc	V _{тв} = 3.08B; V _{DD} = 1.2 5.5B; I _{CC} < 12 мкА		GND • RES • MR • VC
KACW	MAX6805US44D3	MAX	mrc	V _{тв} = 4.38B; V _{DD} = 1.25.5B; I _{CC} < 12 мкА		GND • RES • MR • VC
KACX	MAX6805US46D3	MAX	mrc	V _{тв} = 4.63B; V _{пр} = 1.25.5B; I _{сс} < 12 мкА		GND • RES • MR • VC
L30	BAV23	PHIL	d x2	V _B <200 B; I _F <225 мA; V _F (I _F = 100 мA)< 1.0 B; C _B <5 пФ; t _{BB} <50 нс		K1 • K2 • A2 • A1
L41	BAT74	PHIL	shd x2	$V_R < 30 \text{ B}; I_F < 200 \text{ mA}; V_F (I_F = 1 \text{ mA}) < 320 \text{ mB}; C_D < 10 \text{ n}\Phi; I_{BB} < 5 \text{ HC}$	SOT143, TO253	K1 • K2 • A2 • A1
L51	BAS56	PHIL	fd x2	$V_B < 60 \text{ B; } I_F < 200 \text{ mA; } V_F (I_F = 200 \text{ mA}) < 1.0 \text{ B; } C_D < 2.5 \text{ n}\Phi; I_{BB} < 6 \text{ Hc}$	SOT143, TO253	K1 • K2 • A2 • A1
L51	BAS56	CNTR L	fd x2	V_R <60 B; I_F < 200 mA; V_F (I_F = 200 mA)<1.0 B; C_D <2.5 n Φ ; t_{RS} <6 HC	SOT143, TO253	K1 • K2 • A2 • A1
L51	BAS56	CSI	fid x2	$V_{BR} > 60 \text{ B}$, $I_F < 200 \text{ mA}$, $V_F (I_F = 10 \text{ mA}) < 0.75 \text{ B}$; $I_R < 100 \text{ nA}$; $t_{BR} < 6.0 \text{ nc}$; $C_D < 2.5 \text{ n}\Phi$	SOT143, TO253	A1 • A2 • K2 • K1
М	BAR6507	SIEM	pin x2	$V_R < 30 \text{ B}; I_F < 100 \text{ mA}; V_F (I_F = 50 \text{ mA}) < 1.0 \text{ B}; C_D < 0.9 \text{ n}\Phi$	SOT143, TO253	K1 • K2 • A2 • A1
M01	BF901	PHIL	dnMOS	V _{DS} = 12 B; I _{DS} = 30 мА; P _D = 200 мВт; g _F = 28 мс	SOT143, TO253	S•D•G2•G1
M02	BF901R	PHIL	dnMOS	V _{DS} = 12 B; I _{DS} = 30 мА; P _D = 200 мВт; g _F = 28 мс	SOT143R	S • D • G2 • G1
M04	BF904	PHIL	dnMOS	V _{DS} =7B; I _{DS} =30 mA; P _D =200 mB _T ; g _F =25 mc	SOT143, TO253	S • D • G2 • G1
M06	BF904R	PHIL	dnMOS	V _{DS} = 7B; I _{DS} = 30 мА; P _D = 200 мВт; g _F = 25 мс	SOT143R	S • D • G2 • G1
M26	BF908	PHIL	dnMOS	V _{DS} = 12 B; I _{DS} = 40 мА; P _D = 200 мВт; Q _F = 43 мс	SOT143, TO253	S•D•G2•G1
M27	BF908R	PHIL	dnMOS	V _{DS} = 12 B; I _{DS} = 40 мА; P _D = 200 мВт; g _F = 43 мс	SOT143R	S • D • G2 • G1
M28	BF909	PHIL	dnMOS	V _{DS} = 7B; I _{DS} = 40 мА; P _D = 200 мВт; g _F = 43 мс	SOT143, TO253	S • D • G2 • G1
M29	BF909R	PHIL	dnMOS	V _{DS} = 7B; I _{DS} = 40 mA; P _D = 200 mB _T ; g _F = 43 mc	SOT143R	S • D • G2 • G1
M 31	BSD20	PHIL	nMOS	V _{DS} = 10 B	SOT343, SC82A	G•S•D
M32	BSD22	PHIL	nMOS	V _{DS} = 20 B; I _D = 50 mA; P _D = 230 mBr	SOT143, TO253	SUB • S • D • G
M52	BF992R	PHIL	dnMOS	V _{DS} = 20 B; I _D = 40 mA; P _D = 200 mBt; g _F > 25 mCm	SOT143R	S • D • G2 • G1
M56	BF1100	PHIL	dnMOS	V _{DS} = 14B; I _D = 30 мА; P _D = 200 мВт; g _F = 28 мСм	SOT143, TO253	S•D•G2•G1
M57	BF1100R	PHIL	dnMOS	V _{DS} = 14B; I _D = 30 мА; P _D = 200 мВт; g _E = 28 мСм	SOT143R	S • D • G2 • G1
M74	BSS83	PHIL	nMOS	V _{DS} = 10 B; I _D = 50 mA; P _D = 230 mBT; R _{DS(on)} < 45 Cm	SOT143, TO253	SUB • S • D • G
M87	BF990A	PHIL	dnMOS	V _{DS} = 18 B; I _D = 30 мА; P _D = 200 мВт; NF = 2 дБ; g _E > 18 мСм	SOT143, TO253	S•D•G2•G1
M90	BF990	PHIL	dnMOS	V _{OS} = 18 B; I _O = 30 мА; P _O = 200 мВт; NF = 2 дБ; g _F > 18 мСм	SOT143, TO253	S•D•G2•G1
M 91	BF991	PHIL	dnMOS	V_{DS} = 20 B; I_D = 20 мA; P_D = 200 мВт; NF = 2 дБ; g_F > 14 мСм	SOT143, TO253	S•D•G2•G1
M92	BF992	PHIL	dnMOS	V_{DS} = 20 B; I_D = 40 mA; P_D = 200 mBT; g_F > 25 mCm	SOT143, TO253	S•D•G2•G1
M 94	BF994	PHIL	dnMOS	V_{DS} = 20 B; I_D = 30 mA; P_D = 200 mBT; I_{DS} = 418 mA; g_F > 15 mCm	SOT143, TO253	S•D•G2•G1
M96	BF996	PHIL	dnMOS	V _{DS} = 20 B; I _D = 30 мA; P _D = 200 мВт; NF = 1.8 дБ; I _{DSS} = 220 мA; g _F > 15 мСм	SOT143, TO253	
МАр	BF989	PHIL	dnMOS	$V_{DS} = 20 \text{ B; } I_{DS} = 20 \text{ mA; } P_D = 200 \text{ mBT; } g_F > 12 \text{ mc}$	SOT143, TO253	
ΜВ	BF995	SIEM	dnMOS	V_{DS} = 20 B; I_D = 30 мA; P_D = 200 мBт; NF = 1.1 дБ; I_{DSS} = 420 мA; g_F > 12 мСм	SOT143, TO253	
ИΒ	BF995		dnMOS	V_{DS} = 20 B; I_D = 30 mA; P_D = 200 mBT; I_{DS} = 418 mA; g_F > 12 mCm	SOT143, TO253	
ИB	BF998WR	PHIL	dnMOS	$V_{DS} = 12 \text{ B; } I_D = 30 \text{ mA; } P_D = 200 \text{ mBT; } g_F > 24 \text{mCm}$	SOT343, SC82A	
MB3	ADM811-3TART	AD	mrc	V _{tp} = 3.08B; t _{pps} = 300700 MC; V _{pp} = 15.5B;	COTTAN TONES	GND • RES/RES •





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4
MBB	ADM811RART	AD	mrc	$V_{TR} = 2.63 \text{ B}; t_{RES} = 140560 \text{ MC}; V_{DO} = 15.5 \text{ B}; t_{CC} < 15 \text{ MKA}$	SOT143, TO253	GND • RES/RES • MR • VCC
MBE	ADM811SART	AD	mrc	V_{TR} = 2.93 B; t_{RES} = 140560 MC; V_{DO} = 15.5 B; t_{CC} < 15 MKA	SOT143, TO253	GND • RES/RES • MR • VCC
MBG	ADM811TART	AD	mrc	$V_{TR} = 3.08 \text{ B}; t_{RES} = 140560 \text{ MC}; V_{DO} = 15.5 \text{ B}; t_{CC} < 15 \text{ MKA}$	SOT143, TO253	GND • RES/RES • MR • VCC
MBT	ADM811MART	AD	mrc	V_{TR} = 4.38 B; t_{RES} = 140560 MC; V_{DO} = 15.5 B; t_{CC} < 15 MKA	SOT143, TO253	GND • RES/RES • MR • VCC
MBV	ADM811LART	AD	mrc	V_{TR} = 4.63 B; t_{RES} = 140560 MC; V_{DO} = 15.5 B; t_{CC} < 15 MKA	SOT143, TO253	GND • RES/RES • MR • VCC
MBZ	ADM811ZART	AD	mrc	V_{TR} = 2.32 B; t_{RES} = 140560 MC; V_{DO} = 15.5 B; t_{CC} < 15 MKA	SOT143, TO253	GND • RES/RES • MR • VCC
MC	BF904WR	PHIL	dnMOS	V _{DS} = 7 B; I _{DS} = 30 MA; P _D = 280 MBT; g _F = 25 MC	SOT343R	S•D•G2•G1
MCB	ADM812RART	AD	mrc	$V_{TR} = 2.63 \text{ B}; t_{RES} = 140560 \text{ mc}; V_{DO} = 15.5 \text{ B}; t_{CC} < 15 \text{ m/cA}$	SOT143, TO253	GND • RES/RES • MR • VCC
MCE	ADM812SART	AD	mrc	V_{TR} = 2.93 B; t_{RES} = 140560 MC; V_{DO} = 15.5 B; t_{CC} < 15 MKA	SOT 143, TO253	GND • RES/RES • MR • VCC
MCG	ADM812TART	AD	mrc	$V_{TR} = 3.08 \text{ B; } t_{RES} = 140560 \text{ mc; } V_{DD} = 15.5 \text{ B; } t_{CC} < 15 \text{ mKA}$	SOT143, TO253	GND • RES/RES • MR • VCC
MCT	ADM812MART	AD	mrc	V_{TR} = 4.38 B; t_{RES} = 140560 MC; V_{DO} = 15.5 B; t_{CC} < 15 MKA	SOT143, TO253	GND • RES/RES • MR • VCC
MCV	ADM812LART	AD	mrc	V_{TR} = 4.63 B; t_{RES} = 140560 MC; V_{DO} = 15.5 B; t_{CC} < 15 MKA	SOT143, TO253	GND • RES/RES • MR • VCC
MCZ	ADM812ZART	AD	mrc	V_{TR} = 2.32 B; t_{RES} = 140560 MC; V_{DO} = 15.5 B; t_{CC} < 15 MKA	SOT143, TO253	GND • RES/RES • MR • VCC
MD	BF908WR	PHIL	dnMOS	V _{DS} = 12 B; I _{DS} = 40 mA; P _D = 300 mB _T ; g _F = 43 mc	SOT343R	S•D•G2•G1
MDB	ADM6315-26D1ART	AD	mrc	V _{TR} = 2.63 B; t _{RES} = 1 мс; V _{DD} = 15.5 B; I _{CC} < 15 мкА	SOT143, TO253	GND • RES • MR • VCC
MDC	ADM6315-29D1ART	AD	mrc	V _{TR} = 2.93 B; t _{RES} = 1 мс; V _{DO} = 15.5 B; I _{CC} < 15 мкА	SOT143, TO253	GND • RES • MR • VCC
MDG	ADM6315-31D1ART	AD	mrc	V _{TR} =3.08 B; t _{RES} =1 мс; V _{DD} =15.5 B; I _{CC} < 15 мкА	SOT143, TO253	GND • RES • MR • VCC
MDT	ADM6315-44D1ART	AD	mrc	V _{TR} = 4.39 B; t _{RES} = 1 MC; V _{DD} = 15.5 B; I _{CC} < 15 MKA	SOT143, TO253	GND • RES • MR • VCC
MDU	ADM6315-45D1ART	AD	mrc	V _{TR} =4.5B; t _{RES} =1 MC; V _{DD} =15.5B; I _{CC} <15 MKA	SOT143, TO253	GND • RES • MR • VCC
MDV	ADM6315-46D1ART	AD	mrc	V _{TR} = 4.63 B; t _{RES} = 1 MC; V _{DD} = 15.5 B; I _{CC} < 15 MKA	SOT143, TO253	GND • RES • MR • VCC
MEB	ADM6315-26D2ART	AD	mrc	V _{TR} = 2.63 B; t _{RES} = 20 MC; V _{DD} = 15.5 B; I _{CC} < 15 MKA	SOT143, TO253	GND • RES • MR • VCC
MEC	ADM6315-29D2ART	AD	mrc	V _{TB} = 2.93 B; t _{RES} = 20 MC; V _{DD} = 15.5 B; I _{CC} < 15 MKA	SOT143, TO253	GND • RES • MR • VCC
MEG	ADM6315-31D2ART	AD	mrc	V _{TB} = 3.08 B; t _{BES} = 20 MC; V _{DD} = 15.5 B; I _{CC} < 15 MKA	SOT143, TO253	GND • RES • MR • VCC
MET	ADM6315-44D2ART	AD	mrc	V _{тB} = 4.39 B; t _{BFS} = 20 мс; V _{DD} = 15.5 B; I _{CC} < 15 мкА	SOT143, TO253	GND • RES • MR • VCC
MEU	ADM6315-45D2ART	AD	mrc	V _{TR} =4.5B; t _{RES} =20 MC; V _{DD} =15.5B; I _{CC} <15 MKA	SOT143, TO253	GND • RES • MR • VCC
MEV	ADM6315-46D2ART	AD	mrc	V _{TB} = 4.63 B; t _{BES} = 20 MC; V _{DD} = 15.5 B; I _{CC} < 15 MKA	SOT143, TO253	GND • RES • MR • VCC
MF	BF1100WR	PHIL	dnMOS	V _{DS} = 14B; I _D = 30 мА; P _D = 280 мВт; g _E = 28 мСм	SOT343R	S•D•G2•G1
MFB	ADM6315-26D3ART	AD	mrc	$V_{TB} = 2.63 \text{B}; t_{RFS} = 140 \text{mc}; V_{DD} = 15.5 \text{B}; I_{CC} < 15 \text{mkA}.$	SOT143, TO253	GND • RES • MR • VCC
MFC	ADM6315-29D3ART	AD	mrc	V _{TB} = 2.93 B; t _{BES} = 140 MC; V _{DD} = 15.5 B; I _{CC} < 15 MKA	SOT143, TO253	GND • RES • MR • VCC
MFG	ADM6315-31D3ART	AD	mrc	V _{TB} = 3.08 B; t _{BES} = 140 MC; V _{DD} = 15.5 B; I _{CC} < 15 MKA	SOT143, TO253	GND • RES • MR • VCC
MET	ADM6315-44D3ART	AD	mrc	V _{TB} = 4.39 B; t _{BES} = 140 MC; V _{DD} = 15.5 B; I _{CC} < 15 MKA	SOT143, TO253	GND • RES • MR • VCC
MFU	ADM6315-45D3ART	AD	mrc	V _{TB} =4.5B; t _{RES} =140 MC; V _{DD} =15.5B; I _{CC} <15 MKA	SOT143, TO253	GND • RES • MR • VCC
MFV	ADM6315-46D3ART	AD	mrc	V _{TB} = 4.63 B; t _{BES} = 140 MC; V _{DD} = 15.5 B; I _{CC} < 15 MKA		GND • RES • MR • VCC
MG	BF994S	SIEM	dnMOS	V _{DS} = 20 B; I _D = 30 мA; P _D = 200 мBт; NF = 1 дБ; I _{DSS} = 220 мA; Q _E > 15 мСм		S•D•G2•G1
MG	BF994S	TELEF	dnMOS	V _{DS} =20B; I _D =30 mA; P _D =200 mBt; I _{DS} =418 mA; G _E >15 mCm	SOT143, TO253	S•D•G2•G1
MGB	ADM6315-26D4ART	AD	mrc	V _{TB} = 2.63 B; t _{BES} = 1120 MC; V _{DD} = 15.5 B; I _{DD} < 15 MKA	SOT 143, TO253	GND • RES • MR • VCC
MGC	ADM6315-29D4ART	AD	mrc	V _{TB} = 2.93 B; t _{BES} = 1120 MC; V _{DD} = 15.5 B; I _{CC} < 15 MKA	SOT143, TO253	GND • RES • MR • VCC
MGG	ADM6315-31D4ART	AD	mrc	V _{TB} = 3.08 B; t _{BES} = 1120 MC; V _{DD} = 15.5 B; I _{CC} < 15 MKA		GND • RES • MR • VCC
MGp	BF994S	PHIL	dnMOS	V _{DS} = 20 B; I _D = 30 мA; P _D = 200 мBτ; I _{DS} = 418 мA; S _E > 15 мCм	SOT143, TO253	
MGT	ADM6315-44D4ART	AD	mrc	$V_{TB} = 4.39 \text{ B}; t_{RES} = 1120 \text{ mc}; V_{DO} = 15.5 \text{ B}; I_{CC} < 15 \text{ mkA}$	SOT143, TO253	GND • RES • MR • VCC



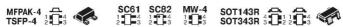


Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1 • 2 • 3 • 4
MGV	ADM6315-46D4ART	AD	mrc	V _{TB} = 4.63B; t _{RES} = 1120 MC; V _{DD} = 15.5B; I _{CC} < 15 MKA	SOT143, TO253	GND • RES • MR • VC
MH	BF996S	SIEM	dnMOS	V _{DS} = 20 B; I _D = 30 мA; P _D = 200 мВт; NF = 1.8 дБ; I _{DSS} = 220 мA; Q _F > 15 мСм	SOT143, TO253	S•D•G2•G1
MH	BF996S	TELEF	dnMOS	V_{DS} = 20 B; I_D = 30 mA; P_D = 200 mB r; I_{DS} = 420 mA; g_F > 15 mCm	SOT143, TO253	S•D•G2•G1
MH	BF996S	VIS	dnMOS	V_{DS} = 20 B; I_D = 30 мA; P_D = 200 мВт; NF = 1.8 дБ; g_F > 18 мСм	SOT143, TO253	S•D•G2•G1
МНр	BF996S	PHIL	dnMOS	V _{DS} = 20 B; I _D = 30 мА; P _D = 200 мВт; NF = 1.8 дБ; g _F > 18 мСм	SOT143, TO253	S•D•G2•G1
MI	2SC4126	REN	npn	V_{CB0} = 15B; I_C = 50 mA; P_D = 150 mBT; h_{21} = 50250; f_T > 4500 MF $_{\rm H}$	SOT343, SC82A	C•E•B•E
MK	BF997	SIEM	dnMOS	V_{DS} = 20 B; I_D = 30 мA; P_D = 200 мBт; NF = 1.0 дБ; I_{DSS} = 220 мA; Q_F > 15мСм	SOT143, TO253	S•D•G2•G1
MO	BF998	VIS	dnMOS	$V_{DS} = 12 \text{ B; } I_D = 30 \text{ mA; } P_D = 200 \text{ mBr; } I_{DS} = 418 \text{ mA; } I_{DS} = 200 \text{ mBr; } I_{DS} = 418 \text{ mA; } I_{DS} = 4$	SOT143, TO253	S•D•G2•G1
МОр	BF998	PHIL	dnMOS	V _{DS} = 12 B; I _D = 30 mA; P _D = 200 mBT; g _F > 24mCm	SOT143, TO253	S•D•G2•G1
МОр	BF998R	PHIL	dnMOS	V _{DS} = 12 B; I _D = 30 мА; P _D = 200 мВт; g _F > 24мСм	SOT143R	S • D • G2 • G1
MOR	BF998R	VIS	dnMOS	V_{DS} = 12 B; I_D = 30 mA; P_D = 200 mB r; I_{DS} = 418 mA; g_F > 21 mCm	SOT143R	S•D•G2•G1
MOs	BF998	INF	dnMOS	V _{DS} = 12 B; I _D = 30 мА; P _D = 200 мВт; NF = 1.0 дБ; I _{DSS} = 220 мА; g _F = 24 мСм	SOT143, TO253	S•D•G2•G1
MR	BF998W	INF	dnMOS	V_{DS} = 12B; I_D = 30 мA; P_D = 200 мBт; NF = 1.0 дБ; I_{DSS} = 218 мA; g_F = 24 мСм	SOT343, SC82A	2 5 232 2
MRs	BF998R	INF	dnMOS	V _{DS} = 12 B; I _D = 30 мА; P _D = 200 мВт; NF = 1.0 дБ; I _{DSS} = 220 мА; g _F = 24 мСм	SOT143R	S•D•G2•G1
Ms	BAR65-07	INF	pin x2	V_B < 30 B; I_F < 100 mA; V_F (I_F = 100 mA) < 1.0 B; C_0 < 0.9 n Φ	SOT143, TO253	K1 • K2 • A2 • A1
MS	CF739	SIEM	nFET	$GaAs; V_{DS} = 10B; I_D = 80 \text{ mA}; P_D = 240 \text{ mBT}; I_{DSS} = 660 \text{ mA}; g_F = 25 \text{ mCm}$	SOT143, TO253	
MX	CF750	SIEM	nFET	GaAs; V_{DS} =8B; I_{D} =80 mA; P_{D} =300 mB+; I_{DSS} =50 mA; g_{F} =25 mCm	SOT143, TO253	GND • D • G • S
MYs	BF1012	SIEM	dnMOS	V_{DS} = 16B; I_D = 25 мA; P_D = 200 мВт; NF = 1.4 дБ; g_F = 26 мСм	SOT143, TO253	
MYs	BF1012W	SIEM	dnMOS	V_{DS} = 16B; I_D = 40 mA; P_D = 200 mB+; NF = 1.4 μ B; g_F = 26mCm	SOT343, SC82A	
MZs	BF1005	SIEM	dnMOS	V_{DS} = 8B; I_D = 25 мA; P_D = 200 мBт; NF = 1.4 дБ; g_F = 24 мСм	SOT143, TO253	
N20	DA227	ROH M	di x2	V_R < 80 B; I_F < 300 mA; P_D < 200 mBT; V_F (I_F = 100 mA) < 1.2 B; t_{PR} < 4 HC		K1 • A1 • A2 • K2
N3	BFG520W	PHIL	npn	V_{CB0} = 20 B; I_C = 70 мA; P_D = 300 мВт; h_{21} > 60; f_T = 9 ГГц	SOT343, SC82A	
N33	BFG505	PHIL	npn	$V_{CB0} = 20B$; $I_C = 18 \text{ mA}$; $P_D = 150 \text{ mBT}$; $h_{21} > 60$; $f_T = 9 \text{ TT} \text{ LL}$	SOT143, TO253	
N36	BFG520	PHIL	npn	V_{CB0} = 20B; I_C = 70 mA; P_D = 300 mBT; h_{21} > 60; f_T = 9 $\Gamma\Gamma I_L$	SOT143, TO253	
N37	BFG540	PHIL	npn	V_{CB0} = 20B; I_C = 120 mA; P_D = 400 mBT; h_{21} > 100; f_T = 9 Γ H_{CB}	SOT143, TO253	
N38	BFG590	PHIL	npn	V_{CB0} =20B; I_C =200 mA; P_D =400 mBT; h_{21} >50; f_T =5 $\Gamma\Gamma u$		
N39	BFG505X	PHIL	npn	$V_{CB0} = 20B$; $I_C = 18 \text{ mA}$; $P_D = 150 \text{ mBT}$; $h_{21} > 60$; $f_T = 9 \text{ TT} \text{ LL}$	SOT143, TO253	NO 21 15417570
N4	BFG520W/X	PHIL	npn	$V_{CB0} = 20B$; $I_C = 70$ mA; $P_D = 300$ mBT; $h_{21} > 60$; $f_T = 9$ TTU	SOT343, SC82A	
N42	BFG520/X	PHIL	npn	$V_{CB0} = 20B; I_C = 70 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 60; f_T = 9 \text{ TT} u$	SOT143, TO253	
N43	BFG540/X	PHIL	npn	V_{CB0} = 20B; I_C = 120 mA; P_D = 400 mBT; h_{21} > 100; f_T = 9 $\Gamma \Gamma U_L$	SOT143, TO253	
N44	BFG590X	PHIL	npn	V_{CB0} = 20B; I_C = 200 mA; P_D = 400 mBT; h_{21} > 50; f_T = 5 $\Gamma\Gamma u$	SOT143, TO253	
N48	BFG520/XR	PHIL	npn	$V_{CB0} = 20B$; $I_C = 70 \text{ mA}$; $P_D = 300 \text{ mBT}$; $h_{21} > 60$; $f_T = 9 \text{ TT} \text{ u}$	SOT143R	C•E•B•E
N49	BFG540/XR	PHIL	npn	V_{CB0} =20B; I_C =120mA; P_D =400mBT; h_{21} >100; f_T =9 $\Gamma\Gamma I_L$	SOT143R	C•E•B•E
N70	BFG10	PHIL	npn	V_{CB0} = 20B; I_C = 250 mA; P_D = 400 mB1; h_{21} > 25; f_T > 1.8 ГГц	SOT143, TO253	100 No. 2003 Carlo
N71	BFG10/X	PHIL	npn	$V_{CB0} = 20B$; $I_C = 250 \text{ mA}$; $P_D = 400 \text{ mB}\tau$; $h_{21} > 25$; $f_T > 1.8 \Gamma\Gamma U$	SOT143, TO253	C•E•B•E





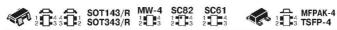
Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4
N72	BFG11	PHIL	npn	$V_{CB0} = 20 \text{ B; } I_C = 500 \text{ mA; } P_D = 400 \text{ mBT; } h_{21} > 25; $ $f_T > 1.8 \text{ IT } I_L$	SOT143, TO253	C•B•E•E
N73	BFG11/X	PHIL	npn	$V_{CB0} = 20 \text{ B; } I_C = 500 \text{ mA; } P_D = 400 \text{ mBr; } h_{21} > 25; $ $f_T > 1.8 \Gamma \text{ II}$	SOT143, TO253	C•E•B•E
NA	BF1105WR	PHIL	dnMOS	V _{DS} = 7 B; I _D = 30 mA; P _D = 200 mBr; g _F = 31 mCm	SOT343R	S•D•G2•G1
NA	CFY35-20	SIEM	nFET	GaAs; V _{DS} =5B; I _D =60 MA; P _D =180 MBT; NF=2.0 µG	MW-4	S•D•S•G
NAp	BF1105R	PHIL	dnMOS	V _{DS} =7B; I _D =30 mA; P _D =200 mBt; g _F =31 mCm	SOT143R	S•D•G2•G1
NB	BF1109WR	PHIL	dnMOS	V _{DS} = 11 B; I _D = 30 мА; P _D = 200 мВт; g _F = 30 мСм	SOT343R	S•D•G2•G1
NB	CFY35-23	SIEM	nFET	GaAs; V _{DS} =5B; I _D =60 MA; P _D =180 MBT; NF=2.3 µB	MW-4	S•D•S•G
NBp	BF1109R	PHIL	dnMOS	V _{DS} = 11 B; I _D = 30 mA; P _D = 200 mBr; g _E = 30 mCm	SOT143R	S•D•G2•G1
NEp	BF1105	PHIL	dnMOS	V _{DS} = 7 B; I _D = 30 мА; P _D = 200 мВт; g _E = 31 мСм	SOT143, TO253	S•D•G2•G1
NFp	BF1109	PHIL	dnMOS	V _{DS} = 11 B; I _D = 30 мА; P _D = 200 мВт; g _E = 30 мСм	SOT143, TO253	S•D•G2•G1
NI.	3SK191	REN	nFET	GaAs; V _{DS} = 12.0B; I _D = 80 мA; P _D = 150 мВт; P _G > 12 дБ; NF < 3.0 дБ	SOT343, SC82A	S•D•G2•G1
NYs	BF1012S	SIEM	dnMOS	$V_{DS} = 16B$; $I_D = 25$ мA; $P_D = 200$ мВт; NF = 1.4 дБ; $g_C = 26$ мСм	SOT143, TO253	S•D•G2•G1
NZs	BF1005S	SIEM	dnMOS	V _{DS} =8B; I _D =25 мА; P _D =200 мВт; NF=1.6 дБ; g _F =24 мСм	SOT143, TO253	S•D•G2•G1
P5	HSMS2855	HP	shd x2	V _E (I _E = 1 mA) < 0.25 B; C _T = 0.3 nΦ	SOT 143, TO253	A1 • A2 • K2 • K1
PAs	BFP136W	SIEM	npn	V_{CB0} = 20 B; I_C = 150 mA; P_D = 1000 mBT; h_{21} = 80250; f_T > 5900 MF $_{II}$	SOT343, SC82A	E•C•E•B
PTs	BAR6407	SIEM	pin x2	V_R <200B; I_F <100 mA; V_F (I_F =50 mA)<1.1 B; C_0 <0.35 n Φ ;	SOT143, TO253	K1 • K2 • A2 • A1
PTs	BAR64-07	INF	pin x2	V_R <150B; I_F <100 mA; V_F (I_F =50 mA)<1.1 B; C_0 <0.35 n Φ	SOT143, TO253	K1 • K2 • A2 • A1
QI	2SC4196	REN	npn	$V_{CB0} = 25 \text{ B; } I_C = 50 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} = 50180; $ $f_T > 1800 \text{ MF } q$	SOT343, SC82A	E•B•C•n.c.
QV	1SV298	SANY 0	pin x3	$V_B > 50B$; $I_F < 50$ mA; $V_F (I_F = 50$ mA) = 0.920.97 B; $I_B < 0.1$ mKA	SOT143, TO253	K1, K2 • A3 • A2, K3 • A1
R26	2SC4093Q	NEC	npn	$V_{CB0} = 20 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBr; } h_{21} = 50100; $ $f_T = 7 \text{ TFL}_L$	SOT143, TO253	C•E•B•E
R26	2SC5011Q	NEC	npn	V_{CB0} = 20 B; I_C = 100 mA; P_D = 150 mBr; h_{21} = 50100; f_T = 6.5 $\Gamma \Gamma q$	SOT343, SC82A	
R27	2SC4093R	NEC	npn	V_{CB0} = 20 B; I_C = 100 mA; P_D = 200 mBT; h_{21} = 80160; f_T = 7 $\Gamma\Gamma L_L$	SOT143, TO253	
R27	2SC5011R	NEC	npn	V_{CB0} = 20 B; I_C = 100 mA; P_D = 150 mBr; h_{21} = 80160; f_T = 6.5 $\Gamma\Gamma U_L$	SOT343, SC82A	E•C•E•B
R28	2SC4093S	NEC	npn	V_{CB0} = 20 B; I_C = 100 mA; P_D = 200 mBr; h_{21} = 125250; f_T = 7 $\Gamma\Gamma I_L$	SOT143, TO253	(CAP) 1 (CB) (CB) (CB)
R28	2SC5011S	NEC	npn	V_{CB0} = 20 B; I_C = 100 mA; P_D = 150 mBT; h_{21} = 125250; f_T = 6.5 fTu	SOT343, SC82A	E•C•E•B
R2s	BFP620	SIEM	npn	V_{CB0} =7.5 B; I_C =80 mA; P_D =185 mBT; h_{21} =110270; f_T =65 $\Gamma\Gamma u$	SOT343, SC82A	70 71 0000071
R36	2SC4094Q	NEC	npn	V_{CB_0} = 20 B; I_C = 65 мA; P_D = 200 мВт; h_{21} = 50100; f_T = 9 ГГц	SOT143, TO253	
R36	2SC5012Q	NEC	npn	V_{CB0} = 20 B; I_C = 65 mA; P_D = 150 mBT; h_{21} = 50100; f_T = 9 $\Gamma\Gamma L_L$	SOT343, SC82A	
R37	2SC4094R	NEC	npn	$V_{CB0} = 20 \text{ B; } I_C = 65 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} = 80160; $ $f_T = 9 \Gamma \Gamma I_L$	SOT143, TO253	
R37	2SC5012R	NEC	npn	V_{CB0} = 20 B; I_C = 65 mA; P_D = 150 mBT; h_{21} = 80160; f_T = 9 $\Gamma\Gamma q$	SOT343, SC82A	
R38	2SC4094S	NEC	npn	$V_{CB0} = 20 \text{ B; } I_C = 65 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} = 125250; $ $f_T = 91 \text{ T}_H$	SOT143, TO253	
738	2SC5012S	NEC	npn	V_{CB0} = 20 B; I_C = 65 mA; P_D = 150 mBT; h_{21} = 125250; f_T = 9 $\Gamma\Gamma$ U	SOT343, SC82A	
R4	2SC4092	NEC	npn	$V_{CB0} = 25 \text{ B}; I_C = 70 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} = 40120; f_T = 6 \text{ TFL}$	SOT143, TO253	C•E•B•E







Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1 • 2 • 3 • 4
R46	2SC4095Q	NEC	npn	$V_{CB0} = 20B$; $I_C = 35 \text{ mA}$; $P_D = 200 \text{ mB} \text{T}$; $h_{21} = 50100$; $f_T = 10 \Gamma \Gamma_H$	SOT143, TO253	C•E•B•E
1 46	2SC5013Q	NEC	npn	$V_{CB0} = 20B$; $I_C = 35 \text{ mA}$; $P_D = 150 \text{ mB}\text{T}$; $h_{21} = 50100$; $f_T = 101 \Gamma \mu$	SOT343, SC82A	E•C•E•B
347	2SC4095R	NEC	npn	$V_{CB0} = 20B$; $I_C = 35 \text{ mA}$; $P_D = 200 \text{ mBr}$; $h_{21} = 80160$; $f_T = 10 \Gamma \Gamma \mu$	SOT143, TO253	C•E•B•E
347	2SC5013R	NEC	npn	$V_{CB0} = 20B$; $I_C = 35 \text{ mA}$; $P_D = 150 \text{ mBT}$; $h_{21} = 80160$; $f_T = 10 \Gamma \Gamma \mu$	SOT343, SC82A	E•C•E•B
348	2SC4095S	NEC	npn	$V_{CB0} = 20B$; $I_C = 35 \text{ mA}$; $P_D = 200 \text{ mBT}$; $h_{21} = 125250$; $f_T = 101 \Gamma I_L$	SOT143, TO253	C•E•B•E
348	2SC5013S	NEC	npn	V_{CB0} = 20B; I_C = 35 mA; P_D = 150 mBT; h_{21} = 125250; f_T = 10 $\Gamma\Gamma\mu$	SOT343, SC82A	E•C•E•B
R4s	BFP640	SIEM	npn	$V_{CB0} = 13B$; $I_C = 50 \text{ mA}$; $P_D = 185 \text{ mBr}$; $h_{21} = 110270$; $f_T = 401 \Gamma \mu$	SOT343, SC82A	B•E•C•E
R5	2SC4092	NEC	npn	$V_{CB0} = 25B$; $I_C = 70 \text{ mA}$; $P_D = 200 \text{ mBT}$; $h_{21} = 100200$; $f_T = 6\Gamma\Gamma I_L$	SOT143, TO253	C•E•B•E
R5	HSMS-8205	HP	shd x2	$V_{BR} > 4B$; $V_F (I_F = 1 \text{ mA}) < 0.35B$; $C_D < 0.26n\Phi$; $R_D = 14 \text{ OM}$	SOT143, TO253	A1 • A2 • K2 • K1
R54	2SC5454	NEC	npn	$V_{CB0} = 9 \text{ B}$; $I_C = 50 \text{ mA}$; $P_D = 200 \text{ mB} \text{ T}$; $h_{21} = 75150$; $f_T = 14.5 \Gamma \Gamma \mu$	SOT143, TO253	C•E•B•E
R54	2SC5750	NEC	npn	$V_{CB0} = 9 \text{ B; } I_C = 50 \text{ mA; } P_D = 200 \text{ mB} \text{ T; } h_{21} = 75150; \\ f_T = 15 \Gamma \Gamma_U$	SOT343, SC82A	C•E•B•E
R54	2SC5751	NEC	npn	$V_{CB0} = 9 \text{ B; } I_C = 50 \text{ mA; } P_D = 205 \text{ mBT; } h_{21} = 75150; $ $f_T = 15 \Gamma \Gamma \mu$	MFPAK-4	E•C•E•B
R54	NE67718	NEC	npn	$V_{CB0} = 9 \text{ B; } I_C = 50 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} = 75150; $ $f_T = 15 \Gamma \Gamma \mu$	SOT343, SC82A	C•E•B•E
R 54	NE67739	NEC	npn	$V_{DB0} = 9 \text{ B}$, $I_C = 50 \text{ mA}$; $P_D = 200 \text{ mB} \tau$; $h_{21} = 75150$; $f_T = 14.5 \Gamma \Gamma \mu$	SOT143, TO253	C•E•B•E
R54	NE677M04	NEC	npn	$V_{CB0} = 9 \text{ B}; I_C = 50 \text{ mA}; P_0 = 205 \text{ mB} \text{ T}; h_{21} = 75150; f_T = 15 \Gamma \Gamma_U$	MFPAK-4	E•C•E•B
R55	2SC5455	NEC	npn	$V_{CB0} = 9 \text{ B}, I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} = 75150; f_T = 12 \Gamma \Gamma_U$	SOT143, TO253	C•E•B•E
R55	2SC5752	NEC	npn	$V_{CB0} = 9 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} = 75150; f_T = 12 \Gamma \Gamma_{LI}$	SOT343, SC82A	C•E•B•E
R55	2SC5753	NEC	npn	$V_{CB0} = 9 \text{ B}, I_C = 100 \text{ mA}; P_D = 205 \text{ mB}_T; h_{21} = 75150; f_T = 12 \Gamma \Gamma_U$	MFPAK-4	E•C•E•B
R55	NE67818	NEC	npn	$V_{CB0} = 9 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mB}\text{T}; h_{21} = 75150; f_T = 12 \Gamma \Gamma_U$	SOT343, SC82A	C•E•B•E
R55	NE67839	NEC	npn	$V_{CB0} = 9 \text{ B}$; $I_C = 100 \text{ mA}$; $P_D = 200 \text{ mBT}$; $h_{21} = 75150$; $f_T = 12 \Gamma \Gamma_U$	SOT143, TO253	C•E•B•E
R55	NE678M04	NEC	npn	$V_{CB0} = 9 \text{ B}; I_C = 100 \text{ mA}; P_D = 205 \text{ mBT}; h_{21} = 75150; f_T = 12 \Gamma \Gamma_{IJ}$	MFPAK-4	E•C•E•B
R5s	BFP650	SIEM	npn	V_{CB0} = 13B; I_C = 150 mA; P_D = 500 mB τ ; h_{21} = 110270; f_T = 37 $\Gamma\Gamma\mu$	SOT343, SC82A	B•E•C•E
R66	2SC4091Q	NEC	npn	$V_{CB0} = 15B$; $I_C = 5 \text{ mA}$; $P_D = 50 \text{ mB}\tau$; $h_{21} = 50100$; $f_T > 4 \Gamma \Gamma \mu$	SOT143, TO253	C•E•B•E
R67	2SC4091R	NEC	npn	$V_{CB0} = 15B$; $I_C = 5 \text{ mA}$; $P_D = 50 \text{ mBT}$; $h_{21} = 80160$; $f_T > 4 \Gamma \Gamma L$	SOT143, TO253	C•E•B•E
R68	2SC4091S	NEC	npn	V_{CB0} = 15B; I_C =5 mA; P_D =50 mBT; h_{21} = 125250; f_T >4 $\Gamma\Gamma L_L$	SOT143, TO253	
37	HSMS-8207	HP	shd x4	V _{BR} >4B; V _F (I _F =1 мA)<0.35B; C _D <0.26пФ; R _D =14 Ом	SOT143, TO253	A1, K4 • A2, K1 • A3, K2 • A4, K3
38	BFG93A	PHIL	npn	$V_{CB0} = 15B$; $I_C = 35 \text{ mA}$; $P_D = 300 \text{ mB}_T$; $h_{21} > 40$; $f_T > 4.5 \Gamma \Gamma U$	SOT143, TO253	C•B•E•E
39	HSMS-8209	HP	shd x4	V _{BR} >4B; V _E (I _E =1 мA)<0.35B; C _D <0.26пФ; R _D =14 Ом		A1, K4 • A2, K3 • A3, K1 • A4, K2
RAs	BF772	SIEM	npn	V_{CB0} = 20B; I_C = 80 mA; P_D = 580 mBT; h_{21} = 50200; f_T = 8000 MF $_{II}$	SOT143, TO253	C•E•B•E
RCs	BFP193	SIEM	npn	$V_{CB0} = 20B$; $I_C = 80 \text{ mA}$; $P_D = 580 \text{ mB}\text{T}$; $h_{21} = 50200$; $f_T = 8000 \text{ MF}\text{U}$	SOT143, TO253	C•E•B•E





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4
RCs	BFP193W	SIEM	npn	$V_{CB0} = 20 \text{ B; } I_C = 80 \text{ mA; } P_D = 580 \text{ mBT; } h_{21} = 50200; $ $f_T = 8000 \text{ MF}_{IJ}$	SOT343, SC82A	E•C•E•B
RDs	BFP180	SIEM	npn	$V_{CB0} = 10 \text{ B; } I_C = 4 \text{ mA; } P_D = 30 \text{ mBT; } h_{21} = 30200; \\ f_T = 6200 \text{ MF}_{\text{LL}}$	SOT143, TO253	C•E•B•E
RDs	BFP180W	SIEM	npn	$V_{CB0} = 10 \text{ B; } I_C = 4 \text{ mA; } P_D = 30 \text{ mBr; } h_{21} = 30200; \\ f_T > 6200 \text{ MF } \mu$	SOT343, SC82A	E•C•E•B
REs	BFP280	SIEM	npn	$V_{CB0} = 10 \text{ B; } I_C = 10 \text{ mA; } P_D = 80 \text{ mBT; } h_{21} = 30200; $ $f_T > 7000 \text{ MF } \text{ µ}$	SOT143, TO253	C•E•B•E
REs	BFP280W	SIEM	npn	$V_{CB0} = 10 \text{ B; } I_C = 10 \text{ mA; } P_D = 80 \text{ mBT; } h_{21} = 30200; $ $f_T > 7000 \text{ mF } \mu$	SOT343, SC82A	E•C•E•B
RFs	BFP181	SIEM	npn	$V_{CB0} = 20 \text{ B; } I_C = 20 \text{ mA; } P_D = 175 \text{ mBT; } h_{21} = 50200; \\ f_T = 8000 \text{ MF } q$	SOT143, TO253	C•E•B•E
RFs	BFP181R	SIEM	npn	$V_{CB0} = 20 \text{ B; } I_C = 20 \text{ mA; } P_D = 175 \text{ mBT; } h_{21} = 50200; $ $f_T > 8000 \text{ MF } q$	SOT143, TO253	C•E•B•E
RFs	BFP181W	SIEM	npn	V _{CB0} =20 B; I _C =20 mA; P _D =175 mBT; h ₂₁ =50200; f _T =8000 MFų	SOT343, SC82A	E•C•E•B
RGs	BFP182	SIEM	npn	$V_{CB0} = 20 \text{ B; } I_C = 35 \text{ mA; } P_D = 250 \text{ mBT; } h_{21} = 50200; $ $f_T > 8000 \text{ MF } Q$	SOT143, TO253	C•E•B•E
RGs	BFP182R	SIEM	npn	$V_{CB0} = 20 \text{ B; } I_C = 35 \text{ mA; } P_D = 250 \text{ mBT; } h_{21} = 50200; $ $f_T > 8000 \text{ MF } \mu$	SOT143, TO253	C•E•B•E
RGs	BFP182W	SIEM	npn	$V_{CB0} = 20 \text{ B; } I_C = 35 \text{ mA; } P_D = 250 \text{ mBT; } h_{21} = 50200; $ $f_T > 8300 \text{ MF } q$.	SOT343, SC82A	E•C•E•B
RHs	BFP183	SIEM	npn	V _{CB0} =20 B; I _C =65 mA; P _D =450 mBT; h ₂₁ =50200; f _T =8000 MFų	SOT143, TO253	C•E•B•E
RHs	BFP183R	SIEM	npn	$V_{CB0} = 20 \text{ B; } I_C = 65 \text{ mA; } P_D = 250 \text{ mBT; } h_{21} = 50200; $ $f_T > 8000 \text{ MF } Q$	SOT143, TO253	C•E•B•E
RHs	BFP183W	SIEM	npn	V _{CB0} =20 B; I _C =65 mA; P _D =450 mBT; h ₂₁ =50200; f _T =8000 MFų	SOT343, SC82A	E•C•E•B
RKs	BFP194	SIEM	pnp	V _{CB0} = 20 B; I _C = 100 mA; P _D = 700 mBr; h ₂₁ = 20150; f _T = 5000 MF _U	SOT143, TO253	C•E•B•E
RIs	BFP196	SIEM	npn	V _{CB0} = 20 B; I _C = 100 mA; P _D = 700 mBr; h ₂₁ = 50200; f _T = 7500 MFu	SOT143, TO253	C•E•B•E
RIs	BFP196W	SIEM	npn	$V_{CB0} = 20 \text{ B; } I_C = 100 \text{ mA; } P_D = 700 \text{ mBr; } h_{21} = 50200; $ $f_T > 7200 \text{ MF } I_C$	SOT343, SC82A	E•C•E•B
54	BBY62	PHIL	var x2	V _B <30B; I _F <20 мА; C _{1B} =16.5 пФ; C _{28B} =1.62 пФ; C _{1B} /C _{28B} =8.3	SOT143, TO253	K1 • K2 • A2 • A1
S5	BAT15099	SIEM	shd x2	$V_B < 4B$; $I_F < 110$ mA; $V_F (I_F = 10$ mA) < 0.32 B; $C_D < 0.35$ n Φ	SOT143, TO253	K1 • A2 • K2 • A1
S5s	BAT15-099	INF	shd x2	$V_B \le 4B$; $I_F \le 110$ mA; $V_F (I_F = 10$ mA) ≤ 0.41 B; $C_D \le 0.35$ n Φ	SOT143, TO253	K1 • A2 • K2 • A1
S6	BAT15099R	SIEM	shd x4	$V_B \le 4B$; $I_F \le 110$ mA; $V_F (I_F = 10$ mA) ≤ 0.32 B; $C_D \le 0.38$ n Φ	SOT143, TO253	K1, A4 • A3, K2 • K4 A2 • A1, K3
S6s	BAT15-099R	INF	shd x4	V_B <4B; I_F <110 mA; V_F (I_F =10 mA)<0.41 B; C_D <0.35 n Φ	SOT143, TO253	K1, A4 • A3, K2 • K4 A2 • A1, K3
S7	BAT114-099	SIEM	shd x2	$V_B < 4B$; $I_F < 90$ mA; $V_F (I_F = 10$ mA) < 0.8 B; $I_B = 5$ mkA; $C_D < 0.5$ n Φ	SOT143, TO253	K1 • A2 • K2 • A1
S8	BAT14099R	SIEM	shd x4	V_B < 4 B; I_F < 90 mA; V_F (I_F = 10 mA) < 0.48 B; C_D < 0.38 n Φ	SOT143, TO253	K1, A4 • A3, K2 • K4 A2 • A1, K3
58s	BAT14-099R	INF	shd x4	V_{B} < 4 B; I_{F} < 90 mA; V_{F} (I_{F} = 10 mA) < 0.48 B; C_{D} < 0.38 n Φ	SOT143, TO253	A1, K4 • A3, K2 • K1 A2 • K3, A4
S9	BAT14099	SIEM	shd x2	V _B <4B; I _F <90 mA; V _F (I _F = 10 mA)<0.55 B; C _D <0.35 пФ	SOT143, TO253	K1 •A2 • K2 •A1
SN	BAT63099R	SIEM	shd x4	$I_F \le 50 \text{ mA}; V_F (I_F = 1 \text{ mA}) \le 0.3 \text{ B}; C_D \le 1.1 \text{ n}\Phi$		A3, K1 • A4, K2 • K3 A2 • A1, C4
T5	HSMS2865	HP	shd x2	V _{BR} >5B; V _F (I _F =30 мА)<0.6B; C _D <0.30 пФ; П _D =10 Ом	SOT143, TO253	K1 • K2 • A2 • A1
T78	2SC5507	NEC	npn	$V_{CB0} = 15 \text{ B; } I_C = 12 \text{ mA; } P_D = 39 \text{ mBT; } h_{21} = 50100; $ $f_T > 20 \text{ TFu}$	MFPAK-4	E•C•E•B
T79	2SC5508	NEC	npn	$V_{CB0} = 15B; I_C = 35 \text{ mA}; P_D = 115 \text{ mB}\text{T}; h_{21} = 50100; f_T > 20 \Gamma\Gamma u$	MFPAK-4	E•C•E•B

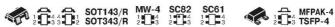
Код	Типономинал	Б	Ф	Особенности	Kopnyc	Ц: 1 • 2 • 3 • 4
Γ8	1SV306	TOSH	var x2	$V_B > 15 B$; $I_B (V_B = 15 B) < 0.003 мкА; C_{2B} = 1416 \pi \Phi; C_{10B} = 5.56.5 \pi \Phi$	SC82, USQ	A1 • A2 • K2 • K1
Г82	2SC4956	NEC	npn	$V_{CB0} = 9 \text{ B}; I_C = 10 \text{ mA}; P_D = 60 \text{ mB}\tau; h_{21} = 75150; f_T = 12 \Gamma \Gamma L_L$	SC61, MPAK-4 C • E • B • E	
82	2SC5014	NEC	npn	$V_{CB0} = 9 \text{ B}; I_C = 10 \text{ mA}; P_D = 60 \text{ mBr}; h_{21} = 75150; f_T = 12 \Gamma \Gamma I_L$	SOT343, SC82A	E•C•E•B
T83	2SC4957	NEC	npn	$V_{CB0} = 9 \text{ B}; I_C = 30 \text{ mA}; P_D = 180 \text{ mBT}; h_{21} = 75150; f_T = 12 \Gamma \Gamma I_L$	SC61, MPAK-4	C•E•B•E
T83	2SC5015	NEC	npn	$V_{CB0} = 9 \text{ B}; I_C = 30 \text{ mA}; P_D = 150 \text{ mB}\tau; h_{21} = 75150; f_T = 12 \Gamma \Gamma L_L$	SOT343, SC82A	E•C•E•B
Г84	2SC5178	NEC	npn	$V_{CB0}=5B$; $I_C=10$ mA; $P_D=30$ mB1; $h_{21}=70140$; $f_1>10.5$ Π_{4}	SOT143, TO253	C•E•B•E
T84	2SC5180	NEC	npn	$V_{CB0}=5 \text{ B; } I_C=10 \text{ mA; } P_D=30 \text{ mBr; } h_{21}=70140; \\ f_T>10 \Gamma \Gamma I_L$	SOT343, SC82A	E•C•E•B
Г86	2SC5183	NEC	npn	$V_{CB0}=5 \text{ B; } I_C=30 \text{ mA; } P_D=90 \text{ mBT; } h_{21}=70140; \\ f_T>9.5 \Gamma\Gamma I_L$	SOT143, TO253	C•E•B•E
T88	2SC5192	NEC	npn	$V_{CB0} = 9 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} = 80160; f_T > 4 \Gamma \Gamma_U$	SOT143, TO253	C•E•B•E
T89	2SC5288	NEC	npn	$V_{CB0} = 9 \text{ B}; I_C = 150 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} > 60$	SOT143, TO253	the region of the region
T90	2SC5289	NEC	npn	$V_{CB0} = 9 \text{ B}; I_C = 300 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} > 60$	SOT143, TO253	28 DE 100 DE
C	2SC2736	REN	npn	V_{CB0} = 30B; I_C =50mA; P_D =150 mBt; h_{21} =30200; f_T > 1400 MF $_{\rm U}$	SOT343, SC82A	Sec. 35 Parallelenses
Π	2SC4197	REN	npn	V_{CB0} = 25B; I_C = 50 mA; P_D = 150 mBT; h_{21} = 50180; f_T > 3 $\Gamma \Gamma q$	SOT343, SC82A	
ΓV	JDV4P08U	TOSH	varx2	V _R <10 B; I _R <0.003 мкА; С _{1 B} =17.319.3 пФ; С _{4 B} =5.36.6		A1 • A2 • K2 • K1
U1A	3SK230UAA	NEC	dnMOS	$V_{\rm DS}$ = 18 B; $I_{\rm D}$ = 25 mA; $P_{\rm D}$ = 200 mB+; $g_{\rm F}$ > 16 mCm; $I_{\rm DSS}$ = 0.013 mA		S • D • G2 • G1
U1B	3SK230UAB	NEC	dnMOS	V_{DS} = 18 B; I_D = 25 mA; P_D = 200 mBT; g_F > 16 mCm; I_{DSS} = 0.013 mA		S•D•G2•G1
U1C	3SK231C	NEC	dnMESFET	$V_{DS} = 18 \text{ B}; I_D = 25 \text{ mA}; P_D = 200 \text{ mBT}; I_{DSS} = 0.0110 \text{ mA}$	SOT143, TO253	
J1D	3SK231D	NEC	dnMESFET	$V_{DS} = 18 \text{ B}; I_D = 25 \text{ mA}; P_D = 200 \text{ mBT}; I_{DSS} = 0.0110 \text{ mA}$	SC61, MPAK-4	S • D • G2 • G1
J1E	3SK252UAE	NEC	dnMOS	$V_{DS} = 18 \text{ B; } I_D = 25 \text{ mA; } P_D = 200 \text{ mBT; } g_F > 14 \text{ mCm; } I_{DSS} = 0.15 \text{ mA}$	SC61, MPAK-4	S•D•G2•G1
U1E	3SK254U1E	NEC	dnMOS	V_{DS} = 18 B; I_D = 25 mA; P_D = 130 mBT; g_F > 14 mCm; I_{DSS} = 0.10.5 mA	SOT343, SC82A	100 St. 100 St
U1G	3SK253UAG	NEC	dnMOS	$V_{DS} = 18 \text{ B; } I_D = 25 \text{ mA; } P_D = 200 \text{ mBT; } g_F > 14 \text{ mCm; } I_{DSS} = 0.57 \text{ mA}$		S • D • G2 • G1
U1G	3SK255U1G	NEC	dnMOS	$V_{DS} = 18 \text{ B; } I_D = 25 \text{ mA; } P_D = 130 \text{ mBT; } g_F > 14 \text{ mCm; } I_{DSS} = 0.17 \text{ mA}$	SOT343, SC82A	
U1s	BGX50A	INF	di x4	V_R <50 В; I_F < 140 мА; V_F (I_F =100 мА)<1.3 В; I_R < 0.2 мкА; C_D <1.5 пФ; t_{RR} <6 нс		K1, K2 • K4, A1 • A4, A3 • A2, K3
U55	3SK134UEE	NEC	dnMOS	V_{DS} =18 B; I_D =25 mA; P_D =200 mBT; g_F >25 mCm; I_{DSS} =0.45 mA	SC61, MPAK-4	S•D•G2•G1
U55	3SK245	NEC	dnMESFET	V _{DS} = 18 B; I _D = 25 mA; P _D = 130 mBt; I _{DSS} = 0.48 mA	SOT343, SC82A	
J56	3SK134UEF	NEC	dnMOS	V_{DS} = 18 B; I_D = 25 mA; P_D = 200 mBT; g_F > 25 mCm; I_{DSS} = 38 mA	SC61, MPAK-4	S•D•G2•G1
J56	3SK245	NEC	dnMESFET	-03	SOT343, SC82A	
J65	3SK135ALS	NEC	dnMOS	V_{DS} = 20 B; I_D = 25 mA; P_D = 200 mBT; g_F > 14 mCm; I_{DSS} = 0.012 mA		S•D•G2•G1
J66	3SK 135AKS	NEC	dnMOS	V_{DS} = 20 B; I_D = 25 mA; P_D = 200 mBT; g_F > 14 mCm; I_{DSS} = 16 mA		S•D•G2•G1
J7	3SK320	TOSH		$V_{DS} = 6B$; $I_D = 18 \text{ mA}$; $P_D = 100 \text{ mB} \text{ T}$; $g_F = 22 \text{ mCm}$	SC82, USQ	G1 • G2 • D • S
J71	3SK177U71	NEC		$V_{DS} = 13 B_1 I_D = 40 \text{mA}; P_D = 200 \text{mB} \tau; g_F > 18 \text{mCm}; I_{DSS} = 515 \text{mA}$	SC61, MPAK-4	S•D•G2•G1
	Lagurage	NEC	dol AFCECT	$V_{DS} = 13 \text{ B}; I_D = 40 \text{ mA}; P_D = 120 \text{ mBT}; g_F > 18 \text{ mCm};$	SULTANA SUBAN	S•D•G2•G1
J71 J72	3SK299 3SK177U72	NEC	dnMESFET	I _{DSS} =515mA V _{DS} =13 B; I _D =40 mA; P _D =200 mBT; g _E >18 mCm;		S•D•G2•G1





	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4
J72	3SK299	NEC	dnMESFET	$V_{DS} = 13 \text{ B}; I_D = 40 \text{ mA}; P_D = 120 \text{ mBT}; g_F > 18 \text{ mCm}; I_{DSS} = 1025 \text{ mA}$	SOT343, SC82A	S•D•G2•G1
J72	NE25118	NEC	nMESFET	GaAs; V _{DS} = 13 B; I _D = 40 мA; P _D = 120 мВт; g _F = 25 мСм	SOT343, SC82A	S•D•G2•G1
J73	3SK177U73	NEC		V_{DS} = 13 B; I_D = 40 mA; P_D = 200 mBT; g_F > 18 mCm; I_{DSS} = 2035 mA		S•D•G2•G1
J73	3SK299	NEC	dnMESFET	$V_{DS} = 13 \text{ B}; I_D = 40 \text{ mA}; P_D = 120 \text{ mBT}; g_F > 18 \text{ mCm}; I_{DSS} = 2035 \text{ mA}$	SOT343, SC82A	S•D•G2•G1
U73	NE25118	NEC	nMESFET	GaAs; V _{DS} = 13 B; I _D = 40 мA; P _D = 120 мBт; g _F = 25 мСм	SOT343, SC82A	
U74	3SK177U74	NEC		$V_{DS} = 13 \text{ B}; I_D = 40 \text{ mA}; P_D = 200 \text{ mBT}; g_F > 18 \text{ mCm}; I_{DSS} = 3040 \text{ mA}$	SC61, MPAK-4	S•D•G2•G1
J74	3SK299	NEC	dnMESFET	$V_{DS} = 13 \text{ B; } I_D = 40 \text{ mA; } P_D = 120 \text{ mBr; } g_F > 18 \text{ mCm; } I_{DSS} = 3040 \text{ mA}$	SOT343, SC82A	S•D•G2•G1
J74	NE25118	NEC	nMESFET	$GaAs;V_{DS} = 13 B;I_D = 40 MA;P_D = 120 MBT;g_F = 25 MCM$	SOT343, SC82A	S•D•G2•G1
J76	3SK206	NEC	dnMESFET	$V_{DS} = 10 \text{ B}; I_D = 80 \text{ mA}; P_D = 200 \text{ mBT}; g_F > 25 \text{ mCm}; I_{DSS} = 1025 \text{ mA}$	SC61, MPAK-4	S•D•G2•G1
J77	3SK206	NEC	dnMESFET	$V_{DS} = 10 \text{ B}; I_D = 80 \text{ mA}; P_D = 200 \text{ mB}_T; g_F > 25 \text{ mCm}; I_{DSS} = 2035 \text{ mA}$	SC61, MPAK-4	S•D•G2•G1
J78	3SK206	NEC	dnMESFET	V_{DS} = 10 B; I_D = 80 mA; P_D = 200 mBT; g_F > 25 mCm; I_{DSS} = 3050 mA	SC61, MPAK-4	S•D•G2•G1
J79	3SK206	NEC	and the little of the little o	V_{DS} = 10 B; I_D = 80 mA; P_D = 200 mBT; g_F > 25 mCm; I_{DSS} = 4580 mA	SC61, MPAK-4	S•D•G2•G1
J87	3SK176AUHG	NEC	dnMOS	V_{DS} = 18 B; I_D = 25 mA; P_D = 200 mBT; g_F > 22 mCm; I_{DSS} = 16 mA	SC61, MPAK-4	S•D•G2•G1
U88	3SK176AUHH	NEC	dnMOS	$V_{DS} = 18 \text{ B}; I_D = 25 \text{ mA}; P_D = 200 \text{ mBT}; g_F > 22 \text{ mCm}; I_{DSS} = 4 10 \text{ mA}$	SC61, MPAK-4	S•D•G2•G1
J90	3SK223UIO	NEC	dnMOS	$V_{DS} = 18 \text{ B}; I_D = 25 \text{ mA}; P_D = 200 \text{ mBT}; g_F > 15 \text{ mCm}; I_{DSS} = 0.013 \text{ mA}$	SC61, MPAK-4	S•D•G2•G1
U90	3SK243	NEC	dnMESFET	V _{DS} = 18 B; I _D = 25 mA; P _D = 200 mBT; I _{DSS} = 0.018 mA	SOT343, SC82A	S•D•G2•G1
J91	3SK223UIA	NEC	dnMOS	V_{DS} = 18 B; I_D = 25 mA; P_D = 200 mBT; g_F > 15 mCm; I_{DSS} = 18 mA	SC61, MPAK-4	S•D•G2•G1
U91	3SK243	NEC	dnMESFET	V _{DS} = 18 B; I _D = 25 мА; P _D = 200 мВт; I _{DSS} = 0.018 мА	SOT343, SC82A	
J94	3SK224UID	NEC	dnMOS	$V_{DS} = 18 \text{ B}; I_D = 25 \text{ mA}; P_D = 200 \text{ mBT}; g_F > 18 \text{ mCm}; I_{DSS} = 0.57 \text{ mA}$	SC61, MPAK-4	S•D•G2•G1
J94	3SK244D	NEC	dnMESFET	V _{DS} = 18 B; I _D = 25 mA; P _D = 130 mBT; I _{DSS} = 0.515 mA	SOT343, SC82A	
J95	3SK224UIE	NEC	dnMOS	V_{DS} = 18 B; I_D = 25 mA; P_D = 200 mBT; g_F > 18 mCm; I_{DSS} = 5 15 mA	SC61, MPAK-4	S•D•G2•G1
J95	3SK244E	NEC	dnMESFET	V _{DS} = 18 B; I _D = 25 mA; P _D = 130 mBT; I _{DSS} = 0.515 mA	SOT343, SC82A	
JF	3SK293		dnMOS	V_{DS} = 12.5 B; I_D = 30 mA; P_D = 100 mB τ ; g_F > 22 mCm; I_{DSS} < 0.1 mA	SC82, USQ	D•S•G1•G2
	3SK260GR		dnMOS	V_{DS} = 13.5 B; I_D = 30 mA; P_D = 100 mBT; g_F = 27 mCm; I_{DSS} = 6 14 mA	SC82, USQ	G1 • G2 • D • S
JHY	3SK260Y		dnMOS	V_{DS} = 13.5 B; I_D = 30 mA; P_D = 100 mBT; g_E = 27 mCm; I_{DSS} = 37 mA	SC82, USQ	G1 • G2 • D • S
JI	3SK259	5.00000	dnMOS	V_{DS} = 13.5 B; I_D = 30 mA; P_D = 100 mBT; g_F = 21 mCm; I_{DSS} < 2 mA	SC82, USQ	G1 • G2 • D • S
JK	3SK294	ATE S	dnMOS	V_{OS} = 12.5 B; I_D = 30 mA; P_D = 100 mBT; g_F > 19.5 mCm; I_{OSS} < 0.1 mA	SC82, USQ	G1 • G2 • D • S
JN	3SK274	TOSH	dnMESFET	$V_{GS} = 9 \text{ B}, I_D = 20 \text{ mA}; P_D = 100 \text{ mBT}; I_{DSS} = 0.48 \text{ mA}; Q_F = 19 \text{ mCm}$	SC82, USQ	G1 • G2 • D • S
JO	3SK249	TOSH	dnMOS	V_{DS} = 12.5 B; I_D = 30 mA; P_D = 100 mBT; g_F > 17 mCm; I_{DSS} = 0.013 mA	SC82, USQ	G1 • G2 • D • S
	3SK256	TOSH	dnMOS	V_{DS} = 13.5 B; I_D = 30 mA; P_D = 100 mBT; g_F = 21.5 mCm; I_{DSS} < 0.1 mA	SC82, USQ	G1 • G2 • D • S
				V = 12 EP.1 = 20(P = 100P = 21C.)	SC82, USQ	G1 • G2 • D • S
UR UT	3SK257	TOSH	dnMOS	$V_{DS} = 13.5 \text{ B}; I_D = 30 \text{ mA}; P_D = 100 \text{ mBT}; g_F = 21 \text{ mCm}$	0002,000	
	3SK257 3SK258		dnMOS	$V_{0S} = 13.5 \text{ B}, I_0 = 30 \text{ MA}, P_0 = 100 \text{ MBT}, g_F = 21 \text{ MCM};$ $V_{0S} = 13.5 \text{ B}, I_0 = 30 \text{ MA}, P_0 = 100 \text{ MBT}, g_F = 13 \text{ MCM};$ $I_{0SS} < 0.1 \text{ MA}$	SC82, USQ	G1 • G2 • D • S

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1 • 2 • 3 • 4
V1.1	3SK242	NEC	dnMOS	V _{DS} = 20 B; I _D = 25 mA; P _D = 130 mBT; I _{DSS} = 725 mA	SOT343, SC82A	S•D•G2•G1
V12	3SK131	NEC	dnMOS	V_{DS} = 20 B; I_D = 25 mA; P_D = 200 mBT; g_F > 22 mCm; I_{DSS} = 1119 mA	SC61, MPAK-4	S•D•G2•G1
/12	3SK242	NEC	dnMOS	V _{DS} = 20 B; I _D = 25 mA; P _D = 130 mBT; I _{DSS} = 725 mA	SOT343, SC82A	S•D•G2•G1
/12	BFG67/X	PHIL	npn	$V_{CB0} = 10B$; $I_C = 50 \text{ mA}$; $P_D = 300 \text{ mBT}$; $h_{21} > 60$; $f_T > 8 \Gamma\Gamma\text{LL}$	SOT143, TO253	C•E•B•E
/13	3SK131	NEC	dnMOS	V_{DS} = 20 B; I_D = 25 mA; P_D = 200 mBT; g_F > 22 mCm; I_{DSS} = 17 25 mA	SC61, MPAK-4	S•D•G2•G1
/13	3SK242	NEC	dnMOS	V _{DS} = 20 B; I _D = 25 мА; P _D = 130 мВт; I _{DSS} = 725 мА	SOT343, SC82A	S•D•G2•G1
/13	BFG197/X	PHIL	npn	V_{CB0} = 20B; I_C = 100 mA; P_D = 350 mBT; h_{21} > 40; f_T = 7.5 ГГц	SOT143, TO253	
/15	BFG93A/X	PHIL	npn	$V_{CB0} = 15B$; $I_C = 35 \text{ mA}$; $P_D = 300 \text{ mB}_T$; $h_{21} > 40$; $f_T > 4.5 \Gamma\Gamma u$		
/21	3SK222VBA	NEC	dnMOS	$V_{DS} = 18 \text{ B}; I_D = 25 \text{ mA}; P_D = 200 \text{ mBT}; g_F > 15 \text{ mCm}; I_{DSS} = 0.013 \text{ mA}$	SC61, MPAK-4	S•D•G2•G1
/21	3SK246	NEC	dnMOS	V _{DS} = 20 B; I _D = 25 мА; P _D = 130 мВт; I _{DSS} = 0.018 мА	SOT343, SC82A	
/22	3SK222VBB	NEC	dnMOS	$V_{DS} = 18 \text{ B; } I_D = 25 \text{ mA; } P_D = 200 \text{ mBr; } g_F > 15 \text{ mCm; } I_{DSS} = 18 \text{ mA}$	SC61, MPAK-4	S•D•G2•G1
122	3SK246	NEC	dnMOS	V _{DS} = 20 B; I _D = 25 mA; P _D = 130 mBT; I _{DSS} = 0.018 mA	SOT343, SC82A	S•D•G2•G1
V26	BFG67/XR	PHIL	npn	$V_{CB0} = 10B$; $I_C = 50 \text{ mA}$; $P_D = 300 \text{ mB}\text{T}$; $h_{21} > 60$; $f_T > 8 \text{ FT u}$.	SOT143R	C•E•B•E
V3	BFG67	VIS	npn	$V_{CB0} = 10B$; $I_C = 50 \text{ mA}$; $P_D = 300 \text{ mBT}$; $h_{21} > 60$; $f_T > 8 \GammaU$	SOT143, TO253	
V3	BFG67	PHIL	npn	$V_{CB0} = 10 \text{ B}; I_C = 50 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 60; f_T > 8 \Gamma\text{LL}$	SOT143, TO253	
V35	BFG197A/XR	PHIL	npn	V_{CB0} = 20B; I_C = 100 mA; P_D = 350 mB1; h_{21} > 40; f_T = 7.5 ГГц	SOT143R	C•E•B•E
/ 5	BFG197	PHIL	npn	V_{CB0} = 20B; I_C = 100 mA; P_D = 350 mBT; h_{21} > 40; f_T = 7.5 ГГц	SOT143, TO253	C•B•E•E
/H-	2SC5624	REN	npn	V_{CB0} = 10B; I_C =35mA; P_D =100 mBT; h_{21} =80160; f_T >25 $\Gamma\Gamma_{IJ}$	SOT343, SC82A	B•E•C•E
VI	2SC4229	REN	npn	V_{CB0} = 30B; I_C = 20mA; P_D = 150 mB τ ; h_{21} = 50180; f_τ > 700 M Γ_{II}	SOT343, SC82A	E•B•C•n. c.
WOF	TSDF1205RW	TELEF	npn	$V_{CB0} = 9 \text{ B}, I_C = 12 \text{ mA}; P_D = 40 \text{ mBr}; h_{21} = 50250; f_T = 12 \Gamma \Gamma_L$	SOT343R	C•E•B•E
W18	BFP181TW	TELEF	npn	V_{CB0} = 15B; I_C = 20 mA; P_D = 160 mBT; h_{21} = 50150; I_T = 8 $\Gamma\Gamma I_U$	SOT343, SC82A	
W22	S822TW	VISH	npn	V_{CB0} = 12B; I_C =8 мA; P_D = 30 мBт; h_{21} =40150; f_T =5.2ГГц	SOT343, SC82A	
W28	BFP280TW	TELEF	0.000	$V_{CB0} = 15B$; $I_C = 10 \text{ mA}$; $P_D = 80 \text{ mB}\tau$; $h_{21} = 50150$; $f_T = 7\Gamma\Gamma L_L$	SOT343, SC82A	
W2F	TSDF1220RW	TELEF	10.000	$V_{CB0} = 9 \text{ B; } I_C = 40 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} = 50150; $ $I_T = 12 \Gamma\Gamma\text{LL}$	SOT343R	C•E•B•E
W4s	BCR400R	INF	abc	V _{CC} <18B; I _{SMIN} =0.1 mA		GND • CONTR • VS • REXT
W4s	BCR400W	INF	abc	V _{CC} <18B; I _{SMIN} =0.1 mA		GND • CONTR • VS • REXT
N67	BFP67W	TELEF	10.5007	V_{CB0} = 20B; I_C = 50 мA; P_D = 200 мВт; h_{21} = 65150; f_T = 7.5 ГГц	SOT343, SC82A	77 77 733373
W82	BFP182TW	TELEF		V_{CB0} = 15B; I_C = 35 mA; P_D = 200 mBr; h_{21} = 50150; f_T = 7.5 $\Gamma\Gamma\mu$	SOT343, SC82A	
K83	BFP183TW	TELEF		V_{CB0} = 15B; I_C =65mA; P_D =200 mBT; h_{21} =50150; f_T =8 $\Gamma\Gamma \chi$	SOT343, SC82A	
N92	BFP92AW	TELEF		V_{CB0} = 20B; I_C = 30mA; P_D = 200 mBT; h_{21} = 50150; f_T = 6 Γ Γ μ	SOT343, SC82A	
WF0	TSDF1205W	TELEF		$V_{CB0} = 9 B_1 I_C = 12 \text{ mA}; P_D = 40 \text{ mBT}; h_{21} = 50250; f_T = 12 \Gamma \Gamma_{LL}$	SOT343, SC82A	
MF2	TSDF1220W	TELEF		$V_{CB0} = 9 \text{ B; } I_C = 40 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} = 50150; \\ f_T = 12 \Gamma \Gamma_{IJ}$	SOT343, SC82A	
WFE	BFP93A	TELEF		V_{CB0} =20B; I_C =50mA; P_D =300mBT; h_{21} =50200; f_T =6 $\Gamma\Gamma I_L$	SOT343, SC82A	
WH-	2SC5623	REN	npn	$V_{CB0} = 10B$; $I_C = 12 \text{ mA}$; $P_D = 50 \text{ mB}\text{T}$; $h_{21} = 60 \dots 140$; $f_T > 23 \Gamma \Gamma I_L$	SOT343, SC82A	B∙E∙C∙E





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4
NI	3SK197	REN	nMOS	V _{DS} = 12 B; I _D = 35 мА; P _D = 150 мВт; P _G = 24.6 дБ; NF = 5.5 дБ	SOT343, SC82A	S•D•G2•G1
MJ-	2SC5894	REN	npn	$V_{CB0} = 12 B; I_C = 12 \text{mA}; P_D = 50 \text{mB}_T; h_{21} = 70150; f_T > 16 \Gamma \Gamma L_L$	SOT343, SC82A	B•E•C•E
OMW	BF998RW	VIS	dnMOS	$V_{DS} = 12 \text{ B}; I_D = 30 \text{ mA}; P_D = 200 \text{ mBT}; I_{DS} = 418 \text{ mA}; $ $g_F > 21 \text{ mCm}$	SOT343R	S•D•G2•G1
WSE	BFP280TRW	TELEF	npn	$V_{CB0} = 15 \text{ B}; I_C = 10 \text{ mA}; P_D = 80 \text{ mBT}; h_{21} = 50150; f_7 = 7 \Gamma \Gamma I_L$	SOT343R	C•E•B•E
NSF	BFP181TRW	TELEF	npn	$V_{CB0} = 15 \text{ B; } I_C = 20 \text{ mA; } P_D = 160 \text{ mBT; } h_{21} = 50150; $ $f_T = 8 \Gamma \Gamma I_L$	SOT343R	C•E•B•E
NSF	S822TRW	VISH	npn	$V_{CB0} = 12 \text{ B; } I_C = 8 \text{ mA; } P_D = 30 \text{ mBT; } h_{21} = 40150; $ $f_T = 5.2 \text{ TC}_{II}$	SOT343R	E•C•E•B
WSG	BFP182TRW	TELEF	npn	$V_{CB0} = 15 \text{ B; } I_C = 35 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} = 50150; $ $f_T = 7.5 \text{ TT}_{II}$	SOT343R	C•E•B•E
NSH	BFP183TRW	TELEF	npn	$V_{CB0} = 15 \text{ B; } I_C = 65 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} = 50150; $ $f_T = 8 \text{ FT} I_L$	SOT343R	C•E•B•E
XB	2SC4416	REN	npn	$V_{CB0} = 25 \text{ B; } I_C = 50 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} = 50180; $ $f_T > 3000 \text{ MF}_U$	SOT343, SC82A	B • E • C • n. c.
XC	2SC4415	REN	npn	$V_{CB0} = 30 \text{ B; } I_C = 20 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} = 50180; $ $f_T > 700 \text{ MFq}$	SOT343, SC82A	C•B•E•B
XE	2SK1092	REN	nFET	GaAs; V_{DS} = 4B; I_D = 150 мA; P_D = 150 мВт; P_G > 8 дБ; NF < 3.5 дБ	SOT343, SC82A	S•D•n. c. •G
XI	3SK196	REN	nMOS	V _{DS} = 12 B; I _D = 35 мА; P _D = 150 мВт; P _G = 32 дБ; NF = 1.0 дБ	SOT343, SC82A	S•D•G2•G1
XM	2SC4591	REN	npn	$V_{CB0} = 15 \text{ B; } I_C = 50 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} = 40250; $ $f_T > 6500 \text{ MFu}$	SOT343, SC82A	E•B•C•n.c.
XN	2SC4592	REN	npn	$V_{CB0} = 15 \text{ B}, I_C = 50 \text{ mA}; P_D = 150 \text{ mB}_T; h_{21} = 40250; f_T > 7000 \text{ MFu}$	SOT343, SC82A	C•E•B•E
XR	3SK228	REN	nFET	GaAs; V_{OS} = 12.0B; I_{O} = 50 мA; P_{O} = 150 мВт; P_{G} > 17 дБ; NF < 2.0 дБ	SOT343, SC82A	S•D•G2•G1
XS	3SK229	REN	nFET	GaAs; V_{OS} = 12.0B; I_D = 50 мА; P_D = 150 мВт; P_G > 17.дБ; NF < 2.0 дБ	SOT343, SC82A	S•D•G2•G1
ΚV	2SC4680	REN	npn	$V_{CB0} = 12 \text{ B; } I_C = 50 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} > 100;$	SOT343, SC82A	E•B•C•n.c.
KV-	3SK309	REN	dnMESFET	$V_{DS} = 6 \text{ B}; I_D = 18 \text{ mA}; P_D = 100 \text{ mBr}; g_F > 30 \text{ mCm}$	SOT343, SC82A	S•G1•G2•D
YB-	3SK318	REN	dnMOS	V _{DS} = 6 B; I _D = 20 mA; P _D = 100 mBr; g _E > 18 mCm	SOT343, SC82A	S•G1•G2•D
YB-	3SK319	REN	dnMOS	V _{DS} = 6 B; I _D = 20 mA; P _D = 100 mBr; g _E > 18 mCm	SC61, MPAK-4	S•G1•G2•D
YJ-	2SC4900	REN	npn	$V_{CB0} = 15 \text{B}; I_C = 50 \text{mA}; P_D = 150 \text{mBT}; h_{21} = 50 250; f_7 > 6 \Gamma \Gamma \text{U}$	SC61, MPAK-4	C•E•B•E
ZD-	2SC5080	REN	npn	$V_{CB0} = 15 \text{ B; } I_C = 50 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} = 50160; $ $f_T > 10.5 \Gamma\Gamma\text{U}$	SC61, MPAK-4	E•C•E•B
ZD-	2SC5081	REN	npn	$V_{CB0} = 15 \text{ B}, I_C = 50 \text{ mA}; P_D = 100 \text{ mB} \text{T}; h_{21} = 50160; f_T > 10.5 \Gamma \Gamma \text{U}$	SOT343, SC82A	E•C•E•B
ZP-	3SK297	REN	dnMOS	$V_{DS} = 12 \text{ B; } I_D = 25 \text{ mA; } P_D = 150 \text{ mBT; } g_F > 16 \text{ mCm; } I_{DSS} = 0.510 \text{ mA}$	SC61, MPAK-4	S•G1•G2•D
ZP-	3SK298	REN	dnMOS	V_{DS} = 12 B; I_D = 25 mA; P_D = 150 mBT; g_F > 16 mCm; I_{DSS} = 0.510 mA	SOT343, SC82A	S•G1•G2•D
ZQ-	3SK295	REN	dnMOS	$V_{DS} = 12 \text{ B}; I_D = 25 \text{ mA}; P_D = 150 \text{ mBT}; g_F > 16 \text{ mCm}; I_{DSS} = 0.510 \text{ mA}$	SC61, MPAK-4	S•G1•G2•D
ZQ-	3SK296	REN	dnMOS	$V_{DS} = 12 \text{ B}; I_D = 25 \text{ mA}, P_D = 150 \text{ mB} \text{ T}; g_F > 16 \text{ mCm}; I_{DSS} = 0.510 \text{ mA}$	SOT343, SC82A	S•G1•G2•D
ZR-	3SK300	REN	dnMOS	V _{DS} = 14 B; I _D = 25 mA; P _D = 150 mBT; g _E > 20 mCm	SC61, MPAK-4	S•G1•G2•D
ZR-	3SK317	REN	dnMOS	V _{DS} = 14 B; I _D = 25 mA; P _D = 100 mB _T ; g _E > 20 mCm	SOT343, SC82A	S•G1•G2•D
ZS-	2SC5545	REN	npn	$V_{CB0} = 15 \text{ B}; I_C = 50 \text{ mA}; P_D = 150 \text{ mBT}; h_{21} = 80160; f_T > 10 \text{ TL}_1$	SC61, MPAK-4	B•C•E•C





SOT23-5, SOT353/553...

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5
#CGA	AD7415ARTZ	AD	dts	10-pasp.; SMBus/I ² C; V _{DD} =2.75.5B	SOT23-5	AS • GND • VDD • SDA • SCL
#CGB	AD7415ARTZ	AD	dts	10-pasp.; SMBus/I ² C; V _{DD} =2.75.5 B	SOT23-5	AS • GND • VDD • SDA • SCL
IJ	MC33464N-20CTR	ON	mrc	V _{TR} =2.0B; V _{IN} =0.710B	SOT23-5	RES • IN • GND • n. c. • n. c.
OK .	MC33464N-30CTR	ON	mrc	V _{TR} =3.0B; V _{IN} =0.710B	SOT23-5	RES • IN • GND • n. c. • n. c.
OR OR	MC33464N-20ATR	ON	mrc	V _{TR} =2.0B; V _{IN} =0.710B	SOT23-5	RES • IN • GND • n. c. • n. c.
OS .	MC33464N-30ATR	ON	mrc	V _{TR} = 3.0B; V _{IN} = 0.710B	SOT23-5	RES • IN • GND • n. c. • n. c.
1R	MC33464N-21ATR	ON	mrc	V _{TR} =2.1B; V _{IN} =0.710B	SOT23-5	RES • IN • GND • n. c. • n. c.
21	RN47A1	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 250 \text{ MFu; } R_1 = 4.7 \text{ kOm}$	SOT353, SC88A	E1 • B1 • E2 • C2 • C1, B2
22	RN47A2	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; f_T = 250 \text{ MFu}; R_1 = 22 \text{ kOm}$	SOT353, SC88A	E1 • B1 • E2 • C2 • C1, B2
23	RN47A3	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; f_T = 250 \text{ MFu}; R_1 = 10 \text{ kOm}$	SOT353, SC88A	E1 • B1 • E2 • C2 • C1, B2
24	RN47A4	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBt;}$ $Q1: R_1/R_2 = 47 \text{ kOm}/47 \text{ kOm;}$ $Q2: R_1/R_2 = 10 \text{ kOm}/47 \text{ kOm}$	SOT353, SC88A	E1 • B1 • E2 • C2 • C1, B2
25	RN47A5	TOSH	Dpnp/npn	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; Q1: R_1/R_2 = 47 KOM/47 KOM; Q2: R_1/R_2 = 4.7 KOM/10 KOM	SOT353, SC88A	E1 • B1 • E2 • C2 • C1, B2
44A	RN1544A	TOSH	Dnpn x2	$V_{C80} = 50 B_i I_C = 300 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} = 200700; f_T = 30 MFL; B_1 = 2.2 \text{ kOm}$	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
44B	RN1544B	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B}; I_C = 300 \text{ mA}; P_D = 300 \text{ mB}\tau; h_{21} = 3501200; f_T = 30 \text{ M}\Gamma u; R_T = 2.2 \text{ kOm}$	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
5L	MC33464N-45CTR	ON	mrc	V _{TR} =4.5B; V _{IN} =0.710B	SOT23-5	RES • IN • GND • n. c. • n. c.
5T	MC33464N-45ATR	ON	mrc	V _{TR} =4.5B; V _{IN} =0.710B	SOT23-5	RES • IN • GND • n. c. • n. c.
7 J	MC33464N-27CTR	ON	mrc	V _{TR} =2.7B; V _{IN} =0.710B	SOT23-5	RES • IN • GND • n. c. • n. c.
7R	MC33464N-27ATR	ON	mrc	V _{TR} =2.7B; V _{IN} =0.710B	SOT23-5	RES • IN • GND • n. c. • n. c.
7Z25	NC7SZ125M5X	FAIR	3-stbuff	V _{CC} =1.655.5 B; I _{OUT} =±24 mA	SOT23-5	OE • A • GND • Y • VCC
BT TB	MC33464N-48ATR	ON	mrc	V _{TR} =4.8B; V _{IN} =0.710B	SOT23-5	RES • IN • GND • n. c. • n. c.
9F	MC33464N-09CTR	ON	mrc	V _{TR} = 0.9B; V _{IN} = 0.710B	SOT23-5	RES • IN • GND • n. c. • n. c.
9N	MC33464N-09ATR	ON	mrc	V _{TR} = 0.9B; V _{IN} = 0.710B	SOT23-5	RES • IN • GND • n. c. • n. c.
A03	OPA703NA	TI	OA	R-R; V_{DD} = 412/±2±6B; f_{BD} = 1 MΓц; I_S = 300 мкA; V_{DS} < ±0.75 мB	SOT23-5	OUT • V- • +IN • -IN • V+
A04	OPA704NA	TI	OA	P-R; V_{DD} = 412/±2±6B; f_{BD} = 3MΓμ; I_S = 300 мкA; V_{DS} < ±0.75 мB	SOT23-5	OUT • V- • +IN • -IN • V+
A05	OPA705NA	TI	OA	R-R; V_{DD} = 412/±2±6B; f_{BD} = 1 MF μ ; I_S = 250 mKA; V_{DS} < ±5 mB	SOT23-5	OUT • V- • +IN • -IN • V+
40N	AD8565AKSZ	AD	OA	$f_{BD} = 5 M \Gamma_{U}; P_D = 12 \text{ MBT}; V_{DD} = 4.516 \text{ B}$	SOT353, SC88A	OUT • V+ • +IN • -IN • V-
40P	AD8531ARTZ	AD	OA	f _{BD} = 3 МГц; P _D = 6 мВт; V _{DD} = 2.76В	SOT23-5	OUT A • V - • +IN A • -IN A • V+
AOQ	AD8531AKSZ	AD	OA	$f_{BD} = 3 \text{ MFu}; P_D = 6 \text{ MBT}; V_{DD} = 2.76 \text{ B}$	SOT353, SC88A	OUT A • V - • +IN A • -IN A • V+
A1	1SS308	TOSH		V_R < 80 B; I_F < 300 mA; V_F (I_F = 100 mA) < 1.2 B; I_R < 0.5 mkA; tRR < 4 Hc	SOT23-5	K1 • A • K2 • K3 • K4
A1	FMA1A	ROHM	Dpnp x2	V_{CC} = 50 B; I_{OUT} = 100 mA; P_D = 300 mBT; h_{21} > 56; 22 kOm/22 kOm	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
A 1	UMA1N	ROHM	Dpnp x2	V_{CC} = 50 B; I_{OUT} = 100 mA; P_D = 150 mBT; h_{21} > 56; 22 kOm/22 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
A10	FMA10A	ROHM	Dpnp x2	V_{CC} =50B; I_{OUT} =100 mA; P_D =300 mB1; h_{21} >56; R2/R1=10	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
A10	FMA9A	ROHM	Dpnp x2	V _{CC} =50B; I _{OUT} =100 mA; P _D =300 mBT; h ₂₁ > 56; 10 kOm/10 kOm	SOT23-5	C1 • C2 • B2 • E1, E2 • B1





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3•4•5
A10	UMA10N	ROHM	Dpnp x2	V_{CC} = 50B; I_{OUT} = 100 mA; P_D = 150 mBT; $h_{21} > 56$; $R2/R1$ = 10	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
A10	UMA9N	ROHM	Dpnp x2	V _{CC} =50B; I _{OUT} =100 mA; P _D =150 mBT; h ₂₁ >56; 10 kOm/10 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
A11	EMA11	ROHM	Dрпр x2	V_{CC} = 50B; I_{DUT} = 100 mA; P_D = 150 mBT; h_{21} > 56; 4.7 kOm/47 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
A11	FMA11A	ROHM	Dpnp x2	V_{CC} = 50B; I_{OUT} = 100 mA; P_D = 300 mBT; h_{21} > 56; 4.7 kOm/47 kOm	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
A11	UMA11N	ROHM	Dpnp x2	V _{CC} = 50 B; I _{OUT} = 100 mA; P _D = 150 mBT; h ₂₁ > 56; 4.7 kOm/47 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
A2	1SS309	TOSH	dix4	V_R < 80 B; I_F < 300 mA; V_F (I_F = 100 mA) < 1.2 B; I_R < 0.5 mrA; tRR < 4 Hc	SOT23-5	A1 • K • A2 • A3 • A4
A2	EMA2	ROHM	Dрпр x2	V_{CC} = 50 B; I_{OUT} = 100 mA; P_D = 150 mBT; h_{21} > 68; 47 kOm/47 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
A2	FMA2A	ROHM	Dpnp x2	V _{CC} = 50B; I _{OUT} = 100 mA; P _D = 300 mB r; h ₂₁ > 68; 47 kOm/47 kOm	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
A2	UMA2N	ROHM	Dpnp x2	V _{CC} = 50B; I _{OUT} = 100 mA; P _D = 150 mBT; h ₂₁ > 68; 47 kOm/47 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
A2G	OP179GRT	AD	OA	R-R; V_{DD} =512B; f_{BD} =5MFu; I_S =3.5 mA; V_{DSI} < ±5 mB	SOT23-5	OUT • V+ • +IN • -IN • V-
A3	EMA3	ROHM	Dpnp x2	V _{CC} = 50B; I _{OUT} = 100 mA; P _D = 150 mBt; h ₂₁ > 68; R ₁ 4.7 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
A3	FMA3A	ROHM	Dpnp x2	V _{CC} = 50B; I _{DUT} = 100 mA; P _D = 300 mBT; h ₂₁ > 68; R ₁ 4.7 kOm	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
A3	UMA3N	ROHM	Dpnp x2	V _{CC} = 50B; I _{OUT} = 100 mA; P _D = 150 mBr; h ₂₁ > 68; R ₁ 4.7 KOM	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
A36	OPA336NA	TI	OA	R-R; V _{DD} =2.35.5B; I _S =42mKA; V _{OSI} <±125mKB	SOT23-5	OUT • V - • +IN • -IN • V+
A38	OPA338N	TI	OA	R-R; V _{DD} = 2.55.5 B; f _{BD} = 12.5 MFu; I _S = 2 mA; V _{DS} < ±3.5 mB	SOT23-5	OUT • V - • + IN • - IN • V +
A3A	AD8519ART	AD	OA	f _{BD} =8 МГц; P _D =12 мВт; V _{DD} =2.712 В	SOT23-5	OUT A • V- • +IN A • -IN A • V+
A3B	AD8519AKS	AD	OA	f ₈₀ =8 МГц; Р ₀ =12 мВт; V ₀₀ =2.712 В	SOT353, SC88A	OUT A • V− • +IN A • -IN A • V+
A 4	EMA4	ROHM	Dpnp x2	$V_{CC} = 50B$; $I_{OUT} = 100 \text{ mA}$; $P_D = 150 \text{ mBT}$; $h_{21} > 68$; $R_1 = 10 \text{ kOm}$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
A4	FMA4A	ROHM	Dрпр x2	$V_{CC} = 50B$; $I_{OUT} = 100 \text{ mA}$; $P_D = 300 \text{ mBT}$; $h_{21} > 68$; $R_1 = 10 \text{ kOm}$	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
A4	UMA4N	ROHM	Dрпр x2	$V_{CC} = 50B$; $I_{DUT} = 100 \text{ mA}$; $P_D = 150 \text{ mB}\text{T}$; $h_{21} > 68$; $R_1 10 \text{ kOm}$	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
A40	OPA340NA	П	OA	R-R; V_{DD} = 2.75.5 B; f_{BD} = 5.5 MFu; I_S = 1.1 mA; V_{DS} < ±0.5 mB	SOT23-5	OUT • V- • +IN • -IN • V+
A41	OPA364I	П	OA	R-R; V _{DD} = 1.85.5 B; f _{BD} = 7MFu; I _S = 1.4 mA; V _{DS} < 0.9 mB	SOT23-5	OUT • V- • +IN • -IN • V+
A44	OPA244NA	TI	OA	$V_{DD} = 2.236/\pm 1.1\pm 18 \text{ B}; I_S = 70 \text{ mKA}; V_{DS} < \pm 2 \text{ mB}$	SOT23-5	OUT • V - • +IN • -IN • V+
A47	OPA347NA	TI	OA	R-R; V_{DD} = 2.35.5 B; f_{BD} = 350 kFu; I_S = 43 mkA; V_{DS} < 7 mB	SOT23-5	OUT • V- • +IN • -IN • V+
A48	OPA348AI	П	OA	R-R; V _{DD} =2.15.5 B; f _{BD} =1 MFu; I _S =75 mkA; V _{DS} <6 mB	SOT23-5	OUT • V - • + IN • - IN • V +
A4A	AD8541ART	AD	OA	f _{BD} =1 МГц; P _D =0.3 мВт; V _{DD} =2.75.5 В	SOT23-5	OUT A • V- • +IN A • -IN A • V+
A4B	AD8541AKS	AD	OA	f _{BD} =1 МГц; P _D =0.3 мВт; V _{DD} =2.75.5 В	SOT353, SC88A	OUT A • V- • +IN A • -IN A • V+
A5	EMA5	ROHM	Dpnp x2	$V_{CC} = 50B$; $I_{OUT} = 100$ mA; $P_D = 150$ mBT; $h_{21} > 68$; $R2/R1 = 21$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
A5	FMA5A	ROHM	Dpnp x2	V _{CC} = 50B; I _{OUT} = 100 mA; P _D = 300 mBr; h ₂₁ > 68; R2/R1 = 21	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
A5	UMA5N	ROHM	Dpnp x2	V_{CC} = 50B; I_{OUT} = 100 mA; P_D = 150 mBT; h_{21} > 68; $R2/R1$ = 21	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
A6	FMA6A	ROHM	Dрпр x2	V _{CC} = 50B; I _{DUT} = 100 mA; P _D = 300 mBT; h ₂₁ > 68; R ₁ 47 kOm	SOT23-5	C1 • C2 • B2 • E1, E2 • B1



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1+2+3+4+5
46	UMA6N	ROHM	Dpnp x2	V_{CC} =50B; I_{OUT} =100 mA; P_D =150 mBT; h_{21} >68; P_1 47 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
46A	AD8614ART	AD	OA	f _{BD} = 5.5 МГц; P _D = 20 мВт; V _{DD} = 518 В	SOT23-5	OUT A • V - • +IN • -IN • V+
47	EMA7	ROHM	Dpnp x2	$V_{CC} = 50B$; $I_{OUT} = 100 \text{ mA}$; $P_D = 150 \text{ mBT}$; $h_{21} > 68$; $R2/R1 = 2.1$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
47	FMA7A	ROHM	Dpnp x2	$V_{CC} = 50B$; $I_{OUT} = 100 \text{ mA}$; $P_D = 300 \text{ mB}\text{T}$; $h_{21} > 68$; $R2/R1 = 2.1$	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
47	UMA7N	ROHM	Dpnp x2	V_{CC} =50B; I_{OUT} =100 mA; P_D =150 mBr; h_{21} >68; R2/R1=2.1	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
A7A	AD8531ART	AD	OA	f _{BD} = 3 МГц; P _D = 6 мВт; V _{DD} = 2.76 В	SOT23-5	OUT A • V - • +IN A • -IN A • V+
A7B	AD8531AKS	AD	OA	$f_{BD} = 3 \text{ MFu}; P_D = 6 \text{ MBt}; V_{DD} = 2.76 \text{ B}$	SOT353, SC88A	OUT A • V - • +IN A • -IN A • V+
48	EMA8	ROHM	Dpnp x2	V_{CC} =50B; I_{CUT} =100 mA; P_D =150 mBr; h_{21} >68; R2/R1=4.7	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
48	FMA8A	ROHM	Dpnp x2	V_{CC} =50B; I_{OUT} =100 mA; P_0 =300 mBr; h_{21} >68; R2/R1=4.7	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
48	UMA8N	ROHM	Dpnp x2	V_{CC} =50B; I_{CUT} =100 mA; P_D =150 mBT; h_{21} >68; R2/R1=4.7	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
AAA	AD8601ART	AD	OA	$f_{BD} = 8 M\Gamma_{U}; P_{D} = 6 MBT; V_{DD} = 2.75.5B$	SOT23-5	OUT A • V - • +IN A • -IN • V+
4AA	MAX4450EXK	MAX	OA	R-R; V _{DO} = 4.511/±2.25±5.5B; f _{BD} = 210 MΓυ; V _{DSI} < 26 мB	SOT353, SC88A	OUT • VEE • IN+ • IN- • VCC
AAAA	MAX4501UK	MAX	asw	SPST; R _{ON} < 350 Om; V _{DD} = 212 B	SOT23-5	COM • NO • GND • IN • V+
AAAB	MAX4502UK	MAX	asw	SPST; R _{CN} < 350 OM; V _{DD} = 212 B	SOT23-5	COM • NC • GND • IN • V+
AAAG	MAX4516CUK	MAX	asw	SPST; R _{ON} < 25 O _M ; V _{DD} = ±1±6 B	SOT23-5	COM • NO • V- • IN • V+
AAAH	MAX4517CUK	MAX	asw	SPST; R _{CN} < 25 OM; V _{DD} = ±1±6 B	SOT23-5	COM • NC • V- • IN • V+
AAB	MAX4490AXK	MAX	OA	R-R; V _{DO} = 2.75.5/±1.35±2.75 B; f _{BD} = 10 MFu; V _{DSI} < 16 MB	SOT353, SC88A	IN+•VSS•IN-•OUT•VDD
AABK	MAX2631EUK	MAX	amp	V _{CC} =2.75.5 B; f _P < 900 МГц; I _{CC} =6.6 мА	SOT23-5	SHDN • GND • OUT • VCC • IN
AABL	MAX2632EUK	MAX	amp	V _{CC} =2.75.5 B; f _P < 900 МГц; I _{CC} =6.6 мА	SOT23-5	BIAS • GND • OUT • VCC • IN
AABZ	MAX4200EUK	MAX	buf	$V_{00} = \pm 5 B$; $f_{80} = 780 M \Gamma u$; Gain = 0.96; $V_{08} < 15 M B$	SOT23-5	n. c. • VEE • IN • VCC • OUT
AAC	MAX9075EXK	MAX	стр	P-R; V _{DSI} < ±8 mB; V _{CC} = 2.15.5B; I _{CC} < 6.6 mkA	SOT353, SC88A	OUT • GND • IN+ • IN- • VCC
AAD	AD8601DRT	AD	OA	$f_{BD} = 8 M\Gamma_{U_i} P_D = 6 MB_{T_i} V_{DD} = 2.75.5 B$	SOT23-5	OUT A • V - • +IN A • -IN • V+
4AD	MAX4291EXK	MAX	OA	R-R; V_{DO} = 1.85.5/±0.9±2.75B; f_{BD} = 500 κΓυ; V_{OSI} < 2.5 мB	SOT353, SC88A	IN+ • VEE • IN- • OUT • VCC
AAE	MAX4501EXK	MAX	asw	SPST; R _{DN} < 350 OM; V _{DD} = 212 B	SOT353, SC88A	COM • NO • GND • IN • V+
AAF	MAX4502EXK	MAX	asw	SPST; R _{DN} < 350 OM; V _{DD} = 212 B	SOT353, SC88A	COM • NC • GND • IN • V+
4AFx	SA56606-20	PHIL	mrc	$V_{TR} = 2.0 \text{ B}, V_{DD} = 112 \text{ B}, I_{OUT} < 50 \text{ мA}, x = коддаты$	SOT23-5	VOUT • VDD • VSS • n. c. • n. c.
AAG	MAX4400AXK	MAX	OA	P-R; V _{DO} =2.55.5 B; f _{BD} =800 κΓιι; V _{DSI} <5.5 мB	SOT353, SC88A	IN+•VSS•IN-•OUT•VDD
4AGx	SA56606-27	PHIL	mrc	V _{TR} = 2.7 B; V _{DD} = 112B; I _{OUT} < 50 мA; x = коддаты	SOT23-5	VOUT • VDD • VSS • n. c. • n. c.
AAH	MAX4594EXK	MAX	asw	SPST; R _{ON} < 12 O _M ; V _{DD} = 2.05.5B	SOT353, SC88A	COM • NO • GND • IN • V+
AHX	SA56606-28	PHIL	mrc	$V_{TR} = 2.8 \text{ B; } V_{DD} = 112 \text{ B; } I_{OUT} < 50 \text{ мA; } x = коддаты$	SOT23-5	VOUT • VDD • VSS • n. c. • n. c.
AAI	MAX4595EXK	MAX	asw	SPST; R _{ON} < 12 O _M ; V _{DD} = 2.05.5B	SOT353, SC88A	COM • NC • GND • IN • V+
44.1	MAX4596EXK	MAX	asw	SPST; R _{ON} < 12 Om; V _{DD} = 2.05.5B	SOT353, SC88A	IN • COM • GND • NO • V+
AAJx	SA56606-29	PHIL	mrc	V _{TR} = 2.9 B; V _{DD} = 112 B; I _{OUT} < 50 мА; x = коддаты	SOT23-5	VOUT • VDD • VSS • n. c. • n. c.
44K	MAX4597EXK	MAX	asw	SPST; R _{ON} < 12 O _M ; V _{DD} = 2.05.5B	SOT353, SC88A	IN • COM • GND • NC • V+
44Kx	SA56606-30	PHIL	mrc	V _{TR} =3.0B; V _{DD} =112B; I _{DUT} <50 мA; х — коддаты	SOT23-5	VOUT • VDD • VSS • n. c. • n. c.
AALx	SA56606-31	PHIL	mrc	V _{TR} =3.1B; V _{OO} =112B; I _{OUT} < 50 мA; х — код даты	SOT23-5	VOUT • VDD • VSS • n. c. • n. c.





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1+2+3+4+5
AAMx	SA56606-42	PHIL	mrc	V _{TR} =4.2B; V _{DD} =112B; I _{OUT} < 50 мА; х — код даты	SOT23-5	VOUT •VDD •VSS • n. c. • n. c.
AANx	SA56606-43	PHIL	mrc	V _{TR} =4.3 B; V _{DO} = 112 B; I _{OUT} < 50 мА; х — код даты	SOT23-5	VOUT ◆VDD ◆VSS ◆ n. c. ◆ n. c.
AAPx	SA56606-44	PHIL	mrc	V _{TR} =4.4 B; V _{DD} = 112 B; I _{OUT} < 50 мА; х — код даты	SOT23-5	VOUT ◆VDD ◆VSS ◆ n. c. ◆ n. c.
AARx	SA56606-45	PHIL	mrc	V _{TR} =4.5 B; V _{DD} = 112 B; I _{OUT} < 50 мА; х — код даты	SOT23-5	VOUT ◆VDD ◆VSS ◆ n. c. ◆ n. c.
AASx	SA56606-46	PHIL	mrc	V _{TR} =4.6 B; V ₀₀ = 112 B; I _{OUT} < 50 мА; х — код даты	SOT23-5	VOUT •VDD •VSS • n. c. • n. c.
AATx	SA56606-47	PHIL	mrc	V _{TR} =4.7 B; V _{DO} = 112 B; I _{OUT} < 50 мА; х — код даты	SOT23-5	VOUT • VDD • VSS • n. c. • n. c.
ABAA	MAX4201EUK	MAX	buf	$V_{DD} = \pm 5 B$; $f_{BD} = 780 M \Gamma_H$; $Gain = 0.5$; $R_T = 50 O M$; $V_{DS} < 15 MB$	SOT23-5	n. c. • VEE • IN • VCC • OUT
ABAB	MAX4202EUK	MAX	buf	$V_{DD} = \pm 5 B$; $f_{BD} = 780 M\Gamma_{H}$; $Gain = 0.5$; $R_T = 75 Om$; $V_{DSI} < 15 MB$	SOT23-5	n. c. • VEE • IN • VCC • OUT
ABAF	MAX4212EUK	MAX	OA	R-R; V _{DD} =3.310/±1.65±5 B; f _{BD} =300 MFu; V _{DSI} <12 MB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ABAH	MAX4214EUK	MAX	buf	R-R; V _{DD} =3.1511/±1.575±5.5B; f _{BD} =230 MFu; Gain=2; V _{DSI} <15 MB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ABAJ	MAX4330EUK	MAX	OA	R-R; V _{DD} =2.36.5/±1.15±3.25B; f _{BD} =3MFu; V _{DS} <1.5MB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ABAK	MAX6305UK00D1	MAX	mrc	V _{TR} =2.55B; V _{DO} =15.5B; I _{CC} <16 mkA	SOT23-5	RES • GND • RST IN1 • RST IN2 • VCC
ABAL	MAX6305UK00D2	MAX	mrc	V _{TR} = 2.55B; V ₀₀ = 15.5B; I _{CC} < 16 mkA	SOT23-5	RES • GND • RST IN1 • RST IN2 • VCC
ABAM	MAX6305UK00D3	MAX	mrc	V _{TR} =2.55B; V _{DO} =15.5B; I _{CC} < 16 mkA	SOT23-5	RES • GND • RST IN1 • RST IN2 • VCC
ABBB	MAX6306UK47D2	MAX	mrc	V _{TB} =2.55B; V _{DO} =15.5B; I _{CC} <16 mkA	SOT23-5	RES • GND • MR • RST IN • VCC
ABBG	MAX6306UK46D3	MAX	mrc	V _{TB} =2.55B; V ₀₀ =15.5B; I _{CC} <16 mKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABBO	MAX6306UK44D3	MAX	mrc	V _{TB} =2.55B; V ₀₀ =15.5B; I _{CC} <16 мкA	SOT23-5	RES • GND • MR • RST IN • VCC
ABDO	MAX6306UK31D3	MAX	mrc	V _{TR} =2.55B; V _{DD} =15.5B; I _{CC} <16 мкA	SOT23-5	RES • GND • MR • RST IN • VCC
ABDP	MAX6306UK31D4	MAX	mrc	V _{TB} =2.55B; V _{DD} =15.5B; I _{DD} <16 MKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABDQ	MAX6306UK30D1	MAX	mrc	V _{TB} =2.55B; V _{DD} =15.5B; I _{DD} <16 MKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABDS	MAX6306UK30D3	MAX	mrc	V _{TB} =2.55B; V _{DO} =15.5B; I _{CC} <16 mkA	SOT23-5	RES • GND • MR • RST IN • VCC
ABDW	MAX6306UK29D3	MAX	mrc	V _{TB} =2.55B; V _{DO} =15.5B; I _{DD} < 16 MKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABEA	MAX6306UK28D3	MAX	mrc	V _{TB} =2.55B; V _{DO} =15.5B; I _{CC} <16 mkA	SOT23-5	RES • GND • MR • RST IN • VCC
ABEK	MAX6306UK25D1	MAX	mrc	V _{TB} =2.55B; V _{DO} =15.5B; I _{CC} < 16 mkA	SOT23-5	RES • GND • MR • RST IN • VCC
ABEM	MAX6306UK25D3	MAX	mrc	V _{TB} =2.55B; V _{DO} =15.5B; I _{DC} < 16 mkA	SOT23-5	RES • GND • MR • RST IN • VCC
	MAX6307UK46D3	MAX	mrc	V _{TR} =2.55B; V _{DO} =15.5B; I _{CC} <16 mkA	SOT23-5	RES • GND • RST IN • OVRST IN • VCC
ABFJ	MAX6307UK45D2	MAX	mrc	V _{TR} =2.55B; V _{DO} =15.5B; I _{CC} <16 mkA	SOT23-5	RES • GND • RST IN • OVRST IN • VCC
ABFO	MAX6307UK44D3	MAX	mrc	V _{TR} =2.55B; V _{DO} =15.5B; I _{CC} <16 мкA	SOT23-5	RES • GND • RST IN • OVRST IN • VCC
ABG	MAX9031AXK	MAX	стр	R-R; $V_{DSI} \le \pm 5 \text{ mB}$; $V_{DD} = 2.55.5 \text{ B}$; $I_{DD} \le 55 \text{ mKA}$	SOT353, SC88A	IN+ • VSS • IN- • OUT • VDD
ABGY	MAX6307UK35D3	MAX	mrc	V _{TR} =2.55B; V _{DO} =15.5B; I _{CC} <16 мкA	SOT23-5	RES • GND • RST IN • OVRST IN • VCC
ABH	MAX4412EXK	MAX	OA	R-R; V _{DD} = 2.75.5 B; f _{BD} = 500 MFu; V _{OSI} < 9 mB	SOT353, SC88A	OUT • VEE • IN+ • IN- • VCC
ABI	MAX4452EXK	MAX	OA	R-R; V_{DD} = 2.75.25B; f_{BD} = 200 MFu; V_{DSI} < 12 MB	SOT353, SC88A	OUT • VEE • IN+ • IN- • VCC
ABIO	MAX6308UK00D1	MAX	mrc	V _{TR} =2.55B; V _{DO} =15.5B; I _{CC} <16 мкA	SOT23-5	RES • GND • RST IN1 • RST IN2 • VCC
ABIQ	MAX6308UK00D3	MAX	mrc	V _{TR} =2.55B; V _{DO} =15.5B; I _{CC} <16 мкA	SOT23-5	RES • GND • RST IN1 • RST IN2 • VCC



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1+2+3+4+5
ABJ	MAX4352EXK	MAX	OA	R-R; V _{DD} =2.75.25 B; f _{BD} =80 MFq; V _{OSI} < 12 MB	SOT353, SC88A	OUT • VEE • IN+• IN- • VCC
ABJK	MAX6309UK46D3	MAX	mrc	V _{TR} = 2.55 B; V _{DD} = 15.5 B; I _{CC} < 16 mKA	SOT23-5	RES • GND • MR • RST IN • VCC
4BJL	MAX6309UK46D4	MAX	mrc	V _{TR} = 2.55 B; V _{DD} = 15.5 B; I _{CC} < 16 MKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABJS	MAX6309UK44D3	MAX	mrc	V _{TR} = 2.55 B; V _{DD} = 15.5 B; I _{CC} < 16 MKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABK	MAX985EXK	MAX	стр	$R-R; V_{DSI} \le \pm 7 \text{ mB}; V_{CC} = 2.55.5 \text{ B}; I_{CC} \le 24 \text{ mKA}$	SOT353, SC88A	OUT • VCC • IN+ • IN- • VEE
ABKA	MAX6309UK42D3	MAX	mrc	V _{TB} = 2.55 B; V _{DD} = 15.5 B; I _{CC} < 16 MKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABL	MAX986EXK	MAX	стр	$R-R; V_{DSI} \le \pm 7 \text{ mB}; V_{CC} = 2.55.5 \text{ B}; I_{CC} \le 24 \text{ mKA}$	SOT353, SC88A	OUT • VCC • IN+ • IN- • VEE
ABLM	MAX6309UK32D1	MAX	mrc	V _{TB} = 2.55 B; V _{DD} = 15.5 B; I _{CC} < 16 mKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABLS	MAX6309UK31D3	MAX	mrc	V _{TB} = 2.55 B; V _{DD} = 15.5 B; I _{DD} < 16 mKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABM	MAX987EXK	MAX	стр	$R-R; V_{DSI} \le \pm 7 \text{ mB}; V_{CC} = 2.55.5 \text{ B}; I_{CC} \le 96 \text{ mKA}$	SOT353, SC88A	OUT • VCC • IN+ • IN- • VEE
ABMA	MAX6309UK29D3	MAX	mrc	V _{TB} = 2.55 B; V _{DD} = 15.5 B; I _{DD} < 16 MKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABN	MAX988EXK	MAX	стр	R-R; V _{DSI} < ±7 mB; V _{CC} = 2.55.5B; I _{CC} < 96 mkA	SOT353, SC88A	OUT • VCC • IN+ • IN- • VEE
ABNK	MAX6310UK46D3	MAX	mrc	V _{TR} =2.55 B; V _{DD} =15.5 B; I _{CC} < 16 mKA	SOT23-5	RES • GND • RST IN • OVRST IN • VCC
ABO	MAX6605MXK	MAX	ats	T _{AMB} =-55125°C; V _{CC} =2.75.5B; I _{CC} <10 mA	SOT353, SC88A	VCC • A • OUT • B • GND
ABOH	MAX6310UK40D2	MAX	mrc	$V_{TR} = 2.55 B$; $V_{DD} = 15.5 B$; $I_{CC} \le 16 \text{ MKA}$	SOT23-5	RES • GND • RST IN • OVRST IN • VCC
ABP	MAX9021AXK	MAX	стр	R-R; V_{DSI} < ± 8 mB; V_{DD} = 2.55.5 B; I_{DD} < 5 mKA	SOT353, SC88A	IN+•VSS•IN-•OUT•VDD
ABQ	MAX4484AXK	MAX	OA	R-R; V _{DD} =2.75.5 B; f _{BD} =7 MFu; V _{DSI} <9 mB	SOT353, SC88A	IN+ • VSS • IN- • OUT • VDD
ABQU	MAX6311UK00D3	MAX	mrc	$V_{TR} = 2.55 \text{ B}; V_{DD} = 15.5 \text{ B}; I_{CC} \le 16 \text{ MKA}$	SOT23-5	RES • GND • RST IN1 • RST IN2 • VCC
ABR	MAX4493AXK	MAX	OA	R-R; V _{DD} = ±2.25±5.5 B; f _{BD} = 5 MFu; V _{DSI} < 10 MB	SOT353, SC88A	IN+•VEE•IN-•OUT•VCC
ABRO	MAX6312UK46D3	MAX	mrc	V _{TR} = 2.55 B; V _{DD} = 15.5 B; I _{CC} < 16 MKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABRP	MAX6312UK46D4	MAX	mrc	V _{TR} = 2.55 B; V _{DD} = 15.5 B; I _{CC} < 16 mKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABRW	MAX6312UK44D3	MAX	mrc	V _{TR} = 2.55 B; V _{DD} = 15.5 B; I _{CC} < 16 mKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABS	MAX4470EXK	MAX	OA	R-R; V_{DD} =1.85.5 В; f_{BD} =9 кГц; I_{CC} <1.2 мкА; V_{OSI} <7 мВ	SOT353, SC88A	IN+•VSS•IN-•OUT•VDD
ABSA	MAX6312UK43D3	MAX	mrc	V _{TR} =2.55 B; V _{DD} =15.5 B; I _{CC} < 16 mKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABT	MAX4464EXK	MAX	OA	R-R; V_{DD} =1.85.5 B; f_{BD} =40 kFu; I_{CC} <1.2 mkA; V_{DS} (<7 mB	SOT353, SC88A	IN+•VSS•IN-•OUT•VDD
ABU	MAX4480AXK	MAX	OA	R-R; V _{DD} =2.55.5 B; I _{CC} <100 mkA; V _{DSI} <5.5 mB	SOT353, SC88A	IN+•VSS•IN-•OUT•VDD
ABUE	MAX6312UK29D3	MAX	mrc	V _{TR} =2.55B; V _{DD} =15.5B; I _{CC} <16 mKA	SOT23-5	RES • GND • MR • RST IN • VCC
ABV	MAX3370EXK	MAX	levtrans	RS-232; V _{CC} =2.55.5 B; f _{DR} =2 Мбит/с; I _{CC} <100 мкА	SOT353, SC88A	VL • GND • I/O VL • I/O VCC • VCC
ABVO	MAX6313UK46D3	MAX	mrc	V _{TR} = 2.55 B; V _{DD} = 15.5 B; I _{CC} < 16 MKA	SOT23-5	RES • GND • RST IN • OVRST IN • VCC
ABW	MAX9117EXK	MAX	cmp+vref	$V_{OSI} \le 10 \text{ mB}; V_{CC} = 1.85.5 \text{ B}; V_{REF} = 1.252 \text{ B}; \\ I_{CC} \le 1.6 \text{ mKA}$	SOT353, SC88A	OUT • VEE • IN+ • REF • VCC
ABX	MAX9118EXK	MAX	cmp+vref	$V_{OSI} < 10 \text{ mB}; V_{CC} = 1.85.5 \text{ B}; V_{REF} = 1.252 \text{ B}; \\ I_{CC} < 1.6 \text{ mKA}$	SOT353, SC88A	OUT • VEE • IN+ • REF • VCC
ABY	MAX9119EXK	MAX	стр	V _{OSI} < 10 mB; V _{CC} = 1.85.5 B; I _{CC} < 0.8 mkA	SOT353, SC88A	OUT • VEE • IN+ • IN- • VCC
ABYW	MAX477EUK	MAX	OA	V _{DO} = ±15 B; f _{BD} = 300 МГц; V _{DSI} < 5 мВ	SOT23-5	OUT • VEE • IN+• IN- • VCC
ABYX	MAX4178EUK	MAX	buf	V ₀₀ = ±5 B; f ₈₀ = 330 МГц; V _{OSI} < ±3 мВ	SOT23-5	OUT • VEE • IN • GND • VCC
ABYY	MAX4278EUK	MAX	buf	V ₀₀ = ±5 B; f ₈₀ = 310 МГц; V _{OSI} < 3 мВ	SOT23-5	OUT • VEE • IN • GND • VCC
ABYZ	MAX985EUK	MAX	стр	R-R; V _{DSI} < ±7 mB; V _{CC} = 2.55.5B; I _{CC} < 24 mkA	SOT23-5	OUT • VCC • IN+ • IN- • VEE





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3•4•5
ABZ	MAX9120EXK	MAX	стр	V _{OSI} < 10 mB; V _{CC} = 1.85.5 B; I _{CC} < 0.8 mkA	SOT353, SC88A	OUT • VEE • IN+ • IN- • VCC
ABZA	MAX986EUK	MAX	стр	R-R; V _{OSI} < ±7 mB; V _{CC} = 2.55.5 B; I _{CC} < 24 mkA	SOT23-5	OUT • VCC • IN+ • IN- • VEE
ABZB	MAX987EUK	MAX	cmp	R-R; $V_{OSI} \le \pm 7 \text{ mB}$; $V_{CC} = 2.55.5 \text{ B}$; $I_{CC} \le 96 \text{ mkA}$	SOT23-5	OUT • VCC • IN+ • IN- • VEE
ABZC	MAX988EUK	MAX	стр	R-R; V _{OSI} < ±7 mB; V _{CC} = 2.55.5 B; I _{CC} < 96 mkA	SOT23-5	OUT • VCC • IN+ • IN- • VEE
ABZD	MAX1615EUK	MAX	reg	V _{IN} = 428 BV _{OUT} = 3.3/5 B; I _{OUT} = 30 mA	SOT23-5	IN • GND • OUT • 5/3 (FB) • SHDN
ABZE	MAX1616EUK	MAX	reg	V _{IN} = 428 BV _{OUT} = 1.2428 B; I _{OUT} = 30 mA	SOT23-5	IN • GND • OUT • 5/3 (FB) • SHDN
ABZF	MAX6501UKP035	MAX	tempsw	V _{CC} = 2.75.5B; T _{TH} = +35 °С; I _{CC} < 85 мкА	SOT23-5	GND • GND • HYST • VCC • TOVER
ABZG	MAX6502UKP035	MAX	tempsw	V _{CC} = 2.75.5 B; T _{TH} = +35 °C; I _{CC} < 85 мкА	SOT23-5	GND • GND • HYST • VCC • TOVER
ABZH	MAX8873TUK	MAX	reg	LDO; V _{IN} = 2.5 6.5B; V _{OUT} = 3.15B; I _{OUT} = 120 mA	SOT23-5	IN • GND • SHDN • SET • OUT
ABZI	MAX8873SUK	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =2.88B; I _{OUT} =120 MA	SOT23-5	IN • GND • SHDN • SET • OUT
ABZ.J	MAX8874TUK	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =3.15B; I _{OUT} =120 MA	SOT23-5	IN • GND • SHDN • SET • OUT
ABZK	MAX8874SUK	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =2.88B; I _{OUT} =120 MA	SOT23-5	IN • GND • SHDN • SET • OUT
ABZL	MAX8873RUK	MAX	reg	LDO; V _{IN} =2.56.5B; V _{DUT} =2.8B; I _{DUT} =120mA	SOT23-5	IN • GND • SHDN • SET • OUT
ABZM	MAX8874RUK	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =2.8B; I _{OUT} =120 MA	SOT23-5	IN • GND • SHDN • SET • OUT
ABZP	MAX4012EUK	MAX	OA	R-R; V _{DD} = 3.310/±1.65±5 B; f _{BD} = 200 MFц; V _{DS} < 20 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ABZQ	MAX4014EUK	MAX	OA	R-R; V _{DD} =3.151/±1.575±5.5B; f _{BD} =200 MΓι; V _{OSI} <20 MB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ABZR	MAX6501UKP045	MAX	tempsw	V _{CC} =2.75.5B; T _{TH} =+45°C; I _{CC} <85 mKA	SOT23-5	GND • GND • HYST • VCC • TOVER
ABZS	MAX6501UKP065	MAX	tempsw	V _{CC} = 2.75.5 B; T _{TH} = +65 °C; I _{CC} < 85 MKA	SOT23-5	GND • GND • HYST • VCC • TOVER
ABZT	MAX6501UKP095	MAX	tempsw	V _{CC} = 2.75.5B; T _{TH} = +95 °C; I _{CC} < 85 MKA	SOT23-5	GND • GND • HYST • VCC • TOVER
ABZU	MAX6502UKP045	MAX	tempsw	V _{CC} =2.75.5B; T _{TH} =+45°C; I _{CC} <85 мкА	SOT23-5	GND • GND • HYST • VCC • TOVER
ABZV	MAX6502UKP065	MAX	tempsw	V _{CC} = 2.7 5.5 B; T _{TH} = +65 °C; I _{CC} < 85 MKA	SOT23-5	GND • GND • HYST • VCC • TOVER
ABZW	MAX6502UKP095	MAX	tempsw	V _{CC} = 2.7 5.5 B; T _{TH} = +95 °C; I _{CC} < 85 MKA	SOT23-5	GND • GND • HYST • VCC • TOVER
ABZX	MAX6503UKP005	MAX	tempsw	V _{CC} =2.75.5В; Т _{ТН} =+5°С; I _{CC} <85 мкА	SOT23-5	GND • GND • HYST • VCC • TUNDER
ABZY	MAX6504UKP005	MAX	tempsw	$V_{CC} = 2.7 5.5 B; T_{TH} = +5 °C; I_{CC} < 85 \text{ MKA}$	SOT23-5	GND • GND • HYST • VCC • TUNDER
ACA	MAX5460EXK	MAX	Dpot	32 повиции; 100 кОм; V _{DD} = 2.75.5 В	SC88A	VDD+GND+U/D+CS+H
ACAB	MAX999EUK	MAX	стр	R-R; $V_{OSI} \le \pm 4.5 \text{ mB}$; $V_{DC} = 2.75.5 \text{ B}$; $I_{DC} \le 5 \text{ mA}$	SOT23-5	Q • GND • IN+ • IN- • VCC
ACAG	MAX6501UKP115	MAX	tempsw	V _{CC} =2.75.5В; Т _{ТН} =+115 °С; I _{CC} <85мкА	SOT23-5	GND • GND • HYST • VCC • TOVER
ACAM	MAX6503UKP015	MAX	tempsw	V _{CC} =2.75.5B; T _{TH} =+15 °C; I _{CC} <85 mKA	SOT23-5	GND • GND • HYST • VCC • TUNDER
ACAN	MAX6503UKN005	MAX	tempsw	V _{CC} =2.75.5B; T _{TH} =-5°C; I _{CC} <85mkA	SOT23-5	GND • GND • HYST • VCC • TUNDER
ACAP	MAX6503UKN025	MAX	tempsw	V _{CC} =2.75.5B; T _{TH} =-25°C; I _{CC} <85mkA	SOT23-5	GND ◆GND ◆HYST ◆VCC ◆ TUNDER
	MAX6503UKN035	MAX	tempsw	V _{CC} =2.75.5B; T _{TH} =-35°C; I _{CC} <85mkA	SOT23-5	GND • GND • HYST • VCC • TUNDER
ACAT	MAX6504UKN005	MAX	tempsw	V _{CC} =2.75.5B; T _{TH} =-5°C; I _{CC} <85мкА	SOT23-5	GND • GND • HYST • VCC • TUNDER
ACAV	MAX6504UKN025	MAX	tempsw	V _{CC} =2.75.5B; T _{TH} =-25°C; I _{CC} <85мкА	SOT23-5	GND • GND • HYST • VCC • TUNDER
ACAW	MAX6504UKN035	MAX	tempsw	V _{CC} =2.75.5B; T _{TH} =-35'C; I _{CC} <85мкА	SOT23-5	GND • GND • HYST • VCC • TUNDER
	MAX6504UKN045	MAX	tempsw	V _{CC} =2.75.5B; T _{TH} =-45°C; I _{CC} <85mkA	SOT23-5	GND • GND • HYST • VCC • TUNDER
ACAY	MAX8867UK25	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =2.5B; I _{OUT} =150 mA	SOT23-5	SHDN • GND • IN • OUT • BP
ACAZ	MAX8867UK28	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =2.8B; I _{OUT} =150 mA	SOT23-5	SHDN • GND • IN • OUT • BP
ACB	MAX5463EXK	MAX	Dpot	32 повиции; 50 кОм; V _{DD} = 2.75.5 В	SOT353, SC88A	VDD+GND+U/D+CS+H
ACBA	MAX8867UK29	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =2.84B; I _{OUT} =150 mA	SOT23-5	SHDN • GND • IN • CUT • BP
ACBB	MAX8867UK30	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =3.0B; I _{OUT} =150 mA	SOT23-5	SHDN ● GND ● IN ● OUT ● BP



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5
ACBC	MAX8867UK32	MAX	reg	LDO; V _{IN} = 2.56.5 B; V _{OUT} = 3.15 B; I _{OUT} = 150 mA	SOT23-5	SHDN • GND • IN • OUT • BP
ACBD	MAX8867UK33	MAX	reg	LDO; V _{IN} = 2.5 6.5 B; V _{OUT} = 3.3 B; I _{OUT} = 150 MA	SOT23-5	SHDN • GND • IN • OUT • BP
ACBE	MAX8867UK50	MAX	reg	LDO; V _{IN} = 2.5 6.5 B; V _{DUT} = 5.0 B; I _{DUT} = 150 MA	SOT23-5	SHDN • GND • IN • OUT • BP
ACBF	MAX8868UK25	MAX	reg	LDO; V _{IN} = 2.5 6.5 B; V _{OLIT} = 2.5 B; I _{DLIT} = 150 MA	SOT23-5	SHDN • GND • IN • OUT • BP
ACBG	MAX8868UK28	MAX	reg	LDO; V _{IN} = 2.5 6.5 B; V _{OLIT} = 2.8 B; I _{DLIT} = 150 MA	SOT23-5	SHDN • GND • IN • OUT • BP
ACBH	MAX8868UK29	MAX	reg	LDO; V _{IN} = 2.5 6.5 B; V _{OUT} = 2.84 B; I _{OUT} = 150 mA	SOT23-5	SHDN • GND • IN • OUT • BP
ACBI	MAX8868UK30	MAX	rea	LDO; V _{IN} = 2.5 6.5 B; V _{OUT} = 3.0 B; I _{OUT} = 150 MA	SOT23-5	SHDN • GND • IN • OUT • BP
ACBJ	MAX8868UK32	MAX	reg	LDO; V _{IN} = 2.5 6.5 B; V _{DUT} = 3.15 B; I _{DUT} = 150 MA	SOT23-5	SHDN • GND • IN • OUT • BP
ACBK	MAX8868UK33	MAX	reg	LDO; V _{IN} = 2.5 6.5 B; V _{DUT} = 3.3 B; I _{DUT} = 150 MA	SOT23-5	SHDN • GND • IN • OUT • BP
ACBL	MAX8868UK50	MAX	reg	LDO; V _{IN} = 2.5 6.5 B; V _{OUT} = 5.0 B; I _{OUT} = 150 MA	SOT23-5	SHDN • GND • IN • OUT • BP
ACC	MAX9140EXK	MAX	стр	V _{DSI} < 4.5 mB; V _{CC} = 2.75.5B; I _{CC} < 300 mкA	SOT353, SC88A	OUT • GND • IN+ • IN- • VCC
ACCO	MAX4104EUK	MAX	OA	V _{DO} = ±3.5±5.5 B; f _{BD} = 625 МГц; V _{DSI} < 8 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACCP	MAX4105EUK	MAX	OA	V _{DO} = ±3.5±5.5 B; f _{BD} = 410 МГц; V _{DS} < 8 мВ	SOT23-5	OUT • VEE • IN+• IN- • VCC
ACCQ	MAX4304EUK	MAX	OA	V ₀₀ = ±3.5±5.5 B; f ₈₀ = 730 МГц; V ₀₈ < 8 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACCR	MAX4305EUK	MAX	OA	V _{DO} = ±3.5±5.5 B; f _{BD} = 340 МГц; V _{DSI} < 8 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACCS	MAX4240EUK	MAX	OA	R-R; V _{DD} = 1.85.5/±0.9±2.75B; I _{DD} < 18 mrA; V _{DSI} < 1.4 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACCZ	MAX8867UK36	MAX	reg	LDO; V _{IN} = 2.5 6.5 B; V _{OUT} = 3.6 B; I _{OUT} = 150 MA	SOT23-5	SHDN • GND • IN • OUT • BP
ACDA	MAX8868UK36	MAX	reg	LDO; V _{IN} = 2.5 6.5 B; V _{OUT} = 3.6 B; I _{OUT} = 150 MA	SOT23-5	SHDN • GND • IN • OUT • BP
ACDD	MAX6316LUK46C	MAX	mrc	V _{TR} = 4.63 B; V _{DD} = 15.5 B; I _{CC} < 20 мкА	SOT23-5	RES • GND • MR • WDI • VCC
ACDE	MAX6316LUK29C	MAX	mrc	V _{TR} =2.93B; V _{DD} =15.5B; I _{CC} <20 mKA	SOT23-5	RES • GND • MR • WDI • VCC
ACDF	MAX6316MUK46C	MAX	mrc	V _{TR} =4.63B; V _{DD} =15.5B; I _{CC} <20 мкА	SOT23-5	RES • GND • MR • WDI • VCC
ACDG	MAX6316MUK29C	MAX	mrc	V _{TR} = 2.93B; V _{DD} = 15.5B; I _{CC} < 20 мкА	SOT23-5	RES • GND • MR • WDI • VCC
ACDH	MAX6318LHUK46	MAX	mrc	V _{TR} = 4.63 B; V _{DD} = 15.5 B; I _{CC} < 20 мкА	SOT23-5	RES • GND • RES • WDI • VCC
ACDI	MAX6318LHUK29	MAX	mrc	V _{тв} = 2.93B; V _{DO} = 15.5B; I _{CC} < 20 мкА	SOT23-5	RES • GND • RES • WDI • VCC
ACD.J	MAX6318MHUK46	MAX	mrc	V _{TB} =4.63B; V _{DD} =15.5B; I _{CC} <20 mKA	SOT23-5	RES • GND • RES • WDI • VCC
ACDK	MAX6319LHUK46C	MAX	mrc	V _{TR} =4.63B; V _{DD} =15.5B; I _{CC} < 20 mKA	SOT23-5	RES • GND • RES • MR • VCC
ACDL	MAX6319LHUK29C	MAX	mrc	V _{TB} = 2.93B; V _{DD} = 15.5B; I _{CC} < 20 MKA	SOT23-5	RES • GND • RES • MR • VCC
ACDM	MAX6319MHUK46	MAX	mrc	V _{TB} = 4.63 B; V _{DD} = 15.5 B; I _{CC} < 20 MKA	SOT23-5	RES • GND • RES • MR • VCC
ACDN	MAX6320PUK46C	MAX	mrc	V _{TR} = 4.63 B; V _{DD} = 15.5 B; I _{CC} < 20 мкА	SOT23-5	RES • GND • MR • WDI • VCC
ACDO	MAX6320PUK29C	MAX	mrc	$V_{TB} = 2.93B$; $V_{DD} = 15.5B$; $I_{CC} < 20 \text{ MKA}$	SOT23-5	RES • GND • MR • WDI • VCC
ACDP	MAX6501UKP085	MAX	tempsw	V _{CC} = 2.75.5 B; T _{TH} = +85 °C; I _{CC} < 85 MKA	SOT23-5	GND • GND • HYST • VCC • TOVER
ACDQ	MAX6317HUK46C	MAX	mrc	V ₁₈ =4.63B; V ₀₀ =15.5B; I _{CC} <20 мкА	SOT23-5	RES • GND • MR • WDI • VCC
ACDR	MAX4281EUK	MAX	OA	R-R; V _{DO} = 2.55.5 B; Gain = 1; I _S < 530 mkA; V _{OSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACDS	MAX4174ABUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 1.25; I _S < 530 mkA; V _{DSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACDT	MAX4174ACUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 1.5; I _S < 530 mkA; V _{DSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACDU	MAX4174ADUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 2; I _S < 530 mkA; V _{DSI} < 32.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACDV	MAX4174AEUK	MAX	OA	R-R; V_{DD} = 2.55.5 B; Gain = 2.25; I_S < 530 mkA; V_{DSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+• IN- • VCC
ACDW	MAX4174AFUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 2.5; I _S < 530 мкA; V _{DSI} < 2.5 мB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACDX	MAX4174AGUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 3; I _S < 530 mkA; V _{DSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
	MAX4174AHUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 3.5; I _S < 530 mkA; V _{OSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACDZ	MAX4174AJUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 4; I _S < 530 mkA; V _{OSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEA	MAX4174AKUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 5; I _S < 530 mkA; V _{DSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3•4•5
ACEB	MAX4174ALUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain=6; I _S <530 мкA; V _{DSI} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEC	MAX4174AMUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 7; I _S < 530 мкA; V _{DS} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACED	MAX4174ANUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 9; I _S < 530 мкА; V _{DSI} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
CEE	MAX4174AOUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 10; I _S < 530 мкА; V _{DS} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEF	MAX4174BAUK	MAX	OA	R-R; V _{DD} = 2.55.5 В; Gain = 11; I _S < 530 мкА; V _{DSI} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEG	MAX4174BBUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 13.5; I _S < 530 mrA; V _{DSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEH	MAX4174BCUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 16; I _S < 530 мкА; V _{DS} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEI	MAX4174BDUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 21; I _S < 530 мкА; V _{DS} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEJ	MAX4174BEUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 25; I _S < 530 мкА; V _{DS} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEK	MAX4174BFUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 26; I _S < 530 мкА; V _{DS} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEL	MAX4174BGUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 31; I _S < 530 мкА; V _{DS} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEM	MAX4174BHUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 41; I _S < 530 мкА; V _{DS} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEN	MAX4174BJUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 50; I _S < 530 мкА; V _{OS} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEO	MAX4174BKUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain=51; I _S < 530 мкA; V _{DS} < 2.5 мB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEP	MAX4174BLUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 61; I _S < 530 мкА; V _{DS} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEQ	MAX4174BMUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 80; I _S < 530 мкА; V _{DS} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACER	MAX4174BNUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 100; I _S < 530 мкA; V _{DS} < 2.5 мB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACES	MAX4174CAUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 101; I _S < 530 мкA; V _{DS} < 2.5 мB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACET	MAX4175ABUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 1.25; I _S < 530 мкA; V _{DS} < 2.5 мB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEU	MAX4175ACUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 1.5; I _S < 530 mrA; V _{DS} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEV	MAX4175ADUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 2; I _S < 530 мкA; V _{DS} < 32.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEW	MAX4175AEUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 2.25; I _S < 530 mkA; V _{DS} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEX	MAX4175AFUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 2.5; I _S < 530 мкА; V _{DS} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEY	MAX4175AGUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain=3; I _S <530 мкА; V _{DS} <2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACEZ	MAX4175AHUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 3.5; I _S < 530 mrA; V _{DS} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACF	MAX4350EXK	MAX	OA	R-R; V _{DD} =±4.5±5.5 B; f _{BD} =210MΓu; V _{DS} < 26 мB	SOT353, SC88A	OUT • VEE • IN+ • IN- • VCC
ACFA	MAX4175AJUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain =4; I _S <530 мкA; V _{DS} <2.5 мB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFB	MAX4175AKUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 5; I _S < 530 мкA; V _{DS} < 2.5 мB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFC	MAX4175ALUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 6; I _S < 530 мкA; V _{DS} < 2.5 мB	SOT23-5	OUT • VEE • IN+ • IN- • VCC





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1 • 2 • 3 • 4 • 5
ACFD	MAX4175AMUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 7; I _S < 530 mkA; V _{DSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFE	MAX4175ANUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 9; I _S < 530 mkA; V _{DSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFF	MAX4175AOUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 10; I _S < 530 мкA; V _{DSI} < 2.5 мB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFG	MAX4175BAUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 11; I _S < 530 mcA; V _{DSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFH	MAX4175BBUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 13.5; I _S < 530 mkA; V _{DSI} < 2.5 mB	SOT23-5	OUT ●VEE ● IN+ ● IN- ●VCC
ACFI	MAX4175BCUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 16; I _S < 530 мкA; V _{DSI} < 2.5 мB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFJ	MAX4175BDUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 21; I _S < 530 мкA; V _{DSI} < 2.5 мB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFK	MAX4175BEUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 25; I _S < 530 мкA; V _{DSI} < 2.5 мB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFL	MAX4175BFUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 26; I _S < 530 мкA; V _{DSI} < 2.5 мB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFM	MAX4175BGUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 31; I _S < 530 mkA; V _{DSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFN	MAX4175BHUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain =41; I _S < 530 mkA; V _{DSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFO	MAX4175BJUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 50; I _S < 530 mrA; V _{DSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFP	MAX4175BKUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 51; I _S < 530 mkA; V _{DSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFQ	MAX4175BLUK	MAX	OA	R-R; V _{DO} = 2.55.5 B; Gain = 61; I _S < 530 mrA; V _{OSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFR	MAX4175BMUK	MAX	OA	R-R; V _{DO} = 2.55.5 B; Gain = 80; I _S < 530 mrA; V _{OSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFS	MAX4175BNUK	MAX	OA	R-R; V _{DO} = 2.55.5 В; Gain = 100; I _S < 530 мкА; V _{DSI} < 2.5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFT	MAX4175CAUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 101; I _S < 530 мкA; V _{DS} < 2.5 мB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACFU	MAX6501UKP105	MAX	tempsw	V _{CC} = 2.7 5.5 B; T _{TH} = +105 °C; I _{CC} < 85 mKA	SOT23-5	GND • GND • HYST • VCC • TOVER
ACFV	MAX6501UKP075	MAX	tempsw	V _{CC} = 2.7 5.5 B; T _{TH} = +75 °C; I _{CC} < 85 MKA	SOT23-5	GND • GND • HYST • VCC • TOVER
Charles and	MAX6501UKP055	MAX	tempsw	V _{CC} = 2.75.5 B; T _{TH} = +55 °C; I _{CC} < 85 MKA	SOT23-5	GND • GND • HYST • VCC • TOVER
ACFX	MAX6503UKN015	MAX	tempsw	V _{CC} = 2.75.5 B; T _{TH} = -15 °C; I _{CC} < 85 mkA	SOT23-5	GND • GND • HYST • VCC • TUNDER
ACFY	MAX6502UKP115	MAX	tempsw	V _{CC} = 2.7 5.5 B; T _{TH} = +115 °C; I _{CC} < 85 мкА	SOT23-5	GND • GND • HYST • VCC • TOVER
ACFZ	MAX6502UKP105	MAX	tempsw	V _{CC} = 2.7 5.5 B; T _{TH} = +105 °C; I _{CC} < 85 mkA	SOT23-5	GND • GND • HYST • VCC • TOVER
ACG	MAX4465EXK	MAX	OA	R-R; V _{DD} = 2.45.5 B; f _{BD} = 200 κΓιμ; I _{CC} < 60 мкA; V _{DSI} < 5 мB	SOT353, SC88A	IN+ ● GND ● IN- ● CUT ● VCC
ACGA	MAX6502UKP085	MAX	tempsw	V _{CC} = 2.7 5.5 B; T _{TH} = +85 °C; I _{CC} < 85 MKA	SOT23-5	GND • GND • HYST • VCC • TOVER
ACGB	MAX6502UKP075	MAX	tempsw	V _{CC} = 2.7 5.5 B; T _{TH} = +75 °C; I _{CC} < 85 MKA	SOT23-5	GND • GND • HYST • VCC • TOVER
100000	MAX6502UKP055	MAX	tempsw	V _{CC} = 2.75.5 B; T _{TH} = +55 °C; I _{CC} < 85 MKA	SOT23-5	GND • GND • HYST • VCC • TOVER
	MAX6504UKN015	MAX	tempsw	V _{CC} = 2.75.5 B; T _{TH} = -15 °C; I _{CC} < 85 mkA	SOT23-5	GND • GND • HYST • VCC • TUNDER
ACGE	MAX4322EUK	MAX	OA	R-R; V _{DO} = 2.46.5/±1.2±3.25B; f _{BD} = 5 MFu; V _{DSI} < 3.5 MB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACGF	MAX4040EUK	MAX	OA	R-R; V _{DD} = 2.45.5/±1.2±2.75B; I _S < 20 mkA; V _{DSI} < 2.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ACGJ	MAX6317HUK29C	MAX	mrc	V _{TB} =2.93B; V _{DD} =15.5B; I _{CC} <20 mKA	SOT23-5	RES • GND • MR • WDI • VCC
ACGK	MAX6321HPUK29	MAX	mrc	V _{TR} = 2.93B; V _{DR} = 15.5B; I _{CC} < 20 MKA	SOT23-5	RES • GND • RES • WDI • VCC
	MAX6321HPUK46	MAX	mrc	V _{TB} =4.63B; V _{DD} =15.5B; I _{CC} <20 mKA	SOT23-5	RES • GND • RES • WDI • VCC
100000	MAX6322HPUK29	MAX	mrc	V ₁₈ = 2.93B; V ₀₀ = 15.5B; I _{CC} < 20 мкА	SOT23-5	RES • GND • RES • MR • VCC
	IN PROPERTY OFFE	Introd.	mic	*18 = 000, (00 10.0) 100 × 20 mm	SOT23-5	RES • GND • RES • MR • VCC





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5
ACGY	MAX987EUK	MAX	стр	R-R; V _{OSI} < ±7 mB; V _{CC} = 2.55.5 B; I _{CC} < 96 mKA	SOT23-5	OUT • VCC • IN+ • IN- • VEE
ACH	MAX4466EXK	MAX	OA	R-R; V_{DD} =2.45.5 B; f_{BD} =200 kFu; I_{CC} <60 mkA; V_{DS} <5 mB	SOT353, SC88A	IN+ • GND • IN- • OUT • VCC
ACHF	MAX8867UK27	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =2.7B; I _{OUT} =150mA	SOT23-5	SHDN • GND • IN • OUT • BP
ADA	AD8517ART	AD	OA	f _{BD} =7MГц; P _D =6мВт; V _{DD} =1.86В	SOT23-5	OUT A • V- • +IN A • -IN A • V+
ADIP	MAX6319LHUK49	MAX	mrc	V _{TR} =4.9 B; V _{DD} =15.5 B; I _{CC} < 20 MKA	SOT23-5	RES • GND • RES • MR • VCC
ADIQ	MAX917EUK	MAX	cmp+vref	V_{OSI} < 10 MB; V_{CC} = 1.85.5 B; V_{REF} = 1.245 B; I_{CC} < 1.6 MKA	SOT23-5	OUT • VEE • IN+ • REF • VCC
ADIR	MAX918EUK	MAX	cmp+vref	V_{OSI} < 10 MB; V_{CC} = 1.85.5 B; V_{REF} = 1.245 B; I_{CC} < 1.6 MKA	SOT23-5	OUT • VEE • IN+ • REF • VCC
ADIS	MAX919EUK	MAX	стр	V _{DSI} < 10 mB; V _{CC} = 1.85.5 B; I _{CC} < 0.8 mkA	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ADIT	MAX920EUK	MAX	стр	V _{DSI} < 10 mB; V _{CC} = 1.85.5 B; I _{CC} < 0.8 mkA	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ADIU	MAX4372TEUK	MAX	CSA	V _{DD} = 2.728B; Gain = 20; I _{CC} < 1.9 мА	SOT23-5	GND • OUT • VCC • RS+ • RS-
ADIV	MAX4372FEUK	MAX	CSA	V _{DD} = 2.728B; Gain = 50; I _{CC} < 1.9 мА	SOT23-5	GND • OUT • VCC • RS+ • RS-
ADIW	MAX4372HEUK	MAX	CSA	V _{DD} = 2.728В; Gain = 100; I _{CC} < 1.9 мА	SOT23-5	GND • OUT • VCC • RS+ • RS-
ADIX	MAX1749EUK	MAX	vibdrv	V _{IN} = 2.56.5 B; V _{DUT} = 1.25/1.256.5 B B; I _{OUT} < 120 mA	SOT23-5	ON • GND • IN • OUT • SET
ADIZ	MAX6503UKN045	MAX	tempsw	V _{CC} = 2.75.5B; T _{TH} = -45°C; I _{CC} < 85 mcA	SOT23-5	GND • GND • HYST • VCC • TUNDER
ADJA	MAX4076EUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 1; I _S < 55 mrA; V _{DSI} < 3.5 mB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJB	MAX4074ABUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 1.25; I _S < 55 мкA; V _{DSI} < 3.5 мB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJC	MAX4074ACUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 1.5; I _S < 55 мкA; V _{DS} < 3.5 мB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJD	MAX4074ADUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 2; I _S < 55 mcA; V _{DSI} < 3.5 mB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJE	MAX4074AEUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 2.25; I _S < 55 мкA; V _{DS} < 3.5 мB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJF	MAX4074AFUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 2.5; I _S < 55 мкА; V _{DSI} < 3.5 мВ	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJG	MAX4074AGUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain=3; I _S <55 мкA; V _{DSI} <3.5 мB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJH	MAX4074AHUK	MAX	OA	R-R; V_{DD} =2.55.5 B; Gain =3.5; I_S <55 mkA; V_{DSI} <3.5 mB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJI	MAX4074AJUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain=4; I _S <55 мкA; V _{DSI} <3.5 мB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJJ	MAX4074AKUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain=5; I _S <55 мкA; V _{DSI} <3.5 мB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJK	MAX4074ALUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain=6; I _S <55 мкA; V _{DS} <3.5 мB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJL	MAX4074AMUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain=7; I _S <55 мкA; V _{DS} <3.5 мB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJM	MAX4074ANUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain=9; I _S <55 мкA; V _{DSI} <3.5 мB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJN	MAX4074AOUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 10; I _S < 55 мкA; V _{DSI} < 3.5 мB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJO	MAX4074BAUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 11; I _S < 55 мкA; V _{DSI} < 3.5 мB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJP	MAX4074BBUK	MAX	OA	R-R; V_{DD} = 2.55.5 B; Gain = 13.5; I_S < 55 mrA; V_{DSI} < 3.5 mB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJQ	MAX4074BCUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 16; I _S < 55 мкA; V _{DSI} < 3.5 мB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJR	MAX4074BDUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 21; I _S < 55 мкA; V _{DSI} < 3.5 мB	SOT23-5	OUT • VEE • IN + • IN • VCC
ADJS	MAX4074BEUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 25; I _S < 55 мкA; V _{DSI} < 3.5 мB	SOT23-5	OUT • VEE • IN + • IN • VCC

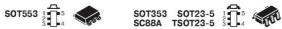


Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1+2+3+4+5
ADJT	MAX4074BFUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 26; I _S < 55 mkA; V _{DSI} < 3.5 mB	SOT23-5	OUT • VEE • IN+• IN • VCC
ADJU	MAX4074BGUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 31; I _S < 55 мкA; V _{OSI} < 3.5 мB	SOT23-5	OUT • VEE • IN+• IN • VCC
ADJV	MAX4074BHUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 41; I _S < 55 мкA; V _{DSI} < 3.5 мB	SOT23-5	OUT • VEE • IN+ • IN • VCC
ADJW	MAX4074BJUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain=50; I _S <55 мкA; V _{OSI} <3.5 мB	SOT23-5	OUT • VEE • IN+ • IN • VCC
ADJX	MAX4074BKUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain=51; I _S <55 мкA; V _{DSI} <3.5 мB	SOT23-5	OUT • VEE • IN+ • IN • VCC
ADJY	MAX4074BLUK	MAX	OA	R-R; V _{DD} =2.55.5 B; Gain = 61; I _S < 55 мкA; V _{DSI} < 3.5 мB	SOT23-5	OUT • VEE • IN+ • IN • VCC
ADJZ	MAX4074BMUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 80; I _S < 55 мкA; V _{DSI} < 3.5 мB	SOT23-5	OUT • VEE • IN+ • IN • VCC
ADKA	MAX4074BNUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 100; I _S < 55 мкA; V _{DSI} < 3.5 мB	SOT23-5	OUT • VEE • IN+• IN • VCC
ADKB	MAX4074CAUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; Gain = 101; I _S < 55 mrA; V _{OSI} < 3.5 mB	SOT23-5	OUT • VEE • IN+ • IN • VCC
ADKC	MAX6318LHUK49	MAX	mrc	V _{TR} = 4.9B; V _{DO} = 15.5B; I _{CC} < 20 MKA	SOT23-5	RES • GND • RES • WDI • VCC
ADKD	MAX8867UK40	MAX	reg	LDO; V _{IN} = 2.5 6.5 B; V _{DUT} = 4.0 B; I _{DUT} = 150 MA	SOT23-5	SHDN • GND • IN • OUT • BP
ADKE	MAX6504UKP015	MAX	tempsw	V _{CC} = 2.7 5.5 B; T _{1H} = +15 °C; I _{CC} < 85 mKA	SOT23-5	GND • GND • HYST • VCC • TUNDER
ADKF	MAX3180EUK	MAX	rec	RS-232; V _{CC} =35.5 B; f _{DR} =1.5 Мбит/с; I _{CC} <5 мкА	SOT23-5	EN • GND • ROUT • RIN • VCC
ADKG	MAX3181EUK	MAX	rec	RS-232; V _{CC} =35.5 В; f _{DR} =1.5 Мбит/с; I _{CC} <5 мкА	SOT23-5	INVALID • GND • ROUT • RIN • VCC
ADKH	MAX3182EUK	MAX	rec	RS-232; V _{CC} =35.5 B; f _{DR} =1.5 Мбит/с; I _{CC} <5 мкА	SOT23-5	EN • GND • ROUT • RIN • VCC
ADKI	MAX3183EUK	MAX	rec	RS-232; V _{CC} =35.5 B; f _{DR} =1.5 Мбит/с; I _{CC} <5 мкА	SOT23-5	INVALID • GND • ROUT • RIN • VCC
ADKJ	MAX6352LSUK	MAX	mrc	$V_{TR1} = 4.63 \text{ B}; V_{TR2} = 2.93 \text{ B}; V_{DD} = 1.25.5 \text{ B}; I_{CC} < 50 \text{ mKA}$	SOT23-5	RST • GND • MR • VCC2 • VCC1
ADKK	MAX6352SYUK	MAX	mrc	$V_{TR1} = 2.93 B$; $V_{TR2} = 2.19 B$; $V_{DD} = 1.25.5 B$; $I_{CC} < 50 \text{ m/sA}$	SOT23-5	RST • GND • MR • VCC2 • VCC1
ADKL	MAX6353LSUK	MAX	mrc	$V_{TRI} = 4.63 \text{ B}; V_{TR2} = 2.93 \text{ B}; V_{DD} = 1.25.5 \text{ B}; V_{CC} < 50 \text{ MKA}$	SOT23-5	RST • GND • MR • VCC2 • VCC1
ADKM	MAX6353SYUK	MAX	mrc	$V_{TR1} = 2.93 B$; $V_{TR2} = 2.19 B$; $V_{DD} = 1.25.5 B$; $I_{CC} < 50 mkA$	SOT23-5	RST • GND • MR • VCC2 • VCC1
ADKN	MAX6354LSUK	MAX	mrc	$V_{TR1} = 4.63 \text{ B}$; $V_{TR2} = 2.93 \text{ B}$; $V_{DD} = 1.25.5 \text{ B}$; $I_{CC} < 50 \text{ MKA}$	SOT23-5	RST • GND • MR • VCC2 • VCC1
ADKO	MAX6354SYUK	MAX	mrc	$V_{TR1} = 2.93 B$; $V_{TR2} = 2.19 B$; $V_{DD} = 1.25.5 B$; $I_{CC} < 50 m \kappa A$	SOT23-5	RST • GND • MR • VCC2 • VCC1
ADKP	MAX4450EUK	MAX	OA	R-R; V_{DD} = 4.511/±2.25±5.5B; f_{BD} = 210 MFu; V_{OSI} < 26 MB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ADKQ	MAX4490AUK	MAX	OA	R-R; V_{DO} = 2.75.5/±1.35±2.75 B; f_{BD} = 10 MFu; V_{DSI} < 16 MB	SOT23-5	IN+ • VSS • IN- • OUT • VDD
ADKR	MAX6316LUK46B	MAX	mrc	V _{TR} = 4.63 B; V _{DD} = 15.5 B; I _{CC} < 20 мкА	SOT23-5	RES • GND • MR • WDI • VCC
ADKS	MAX6306UK47D3	MAX	mrc	V _{TR} =2.55B; V _{DD} =15.5B; I _{CC} <16 mKA	SOT23-5	RES • GND • MR • RST IN • VCC
ADKT	MAX1734EUK33	MAX	dodo	V _{IN} = 2.75.5B; V _{OLIT} = 3.3B; I _{OLIT} = 250 mA	SOT23-5	IN • GND • SHDN • OUT (FB) • LX
ADKU	MAX1734EUK30	MAX	dcdc	V _{IN} = 2.75.5B; V _{OUT} = 3B; I _{OUT} = 250 mA	SOT23-5	IN • GND • SHDN • OUT (FB) • LX
ADKV	MAX1734EUK25	MAX	dodo	V _{IN} = 2.75.5B; V _{DUT} = 2.5B; I _{DUT} = 250 mA	SOT23-5	IN • GND • SHDN • OUT (FB) • LX
ADKW	MAX1734EUK18	MAX	dodo	V _{IN} = 2.75.5B; V _{OUT} = 1.8B; I _{OUT} = 250 mA	SOT23-5	IN • GND • SHDN • OUT (FB) • LX
ADKX	MAX1734EUK15	MAX	dodc	V _{IN} = 2.75.5B; V _{DUT} = 1.5B; I _{DUT} = 250 mA	SOT23-5	IN • GND • SHDN • OUT (FB) • LX
ADKY	MAX1733EUK	MAX	dcdc	V _{IN} = 2.75.5B; V _{DUT} = 1.252B; I _{DUT} = 250 mA	SOT23-5	IN • GND • SHDN • OUT (FB) • LX
ADLM	MAX6318LHUK26C	MAX	mrc	V _{TR} = 2.63 B; V _{DD} = 15.5 B; I _{CC} < 20 mKA	SOT23-5	RES • GND • RES • WDI • VCC
0.000	MAX6318LHUK44C	MAX	mrc	V _{TR} =4.39B; V _{DD} =15.5B; I _{CC} <20 mKA	SOT23-5	RES • GND • RES • WDI • VCC
ADLP	MAX6319LHUK26	MAX	mrc	V _{TB} = 2.63 B; V _{DD} = 15.5 B; I _{CC} < 20 MKA	SOT23-5	RES • GND • RES • MR • VCC





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3•4•5
ADLQ	MAX6319LHUK29	MAX	mrc	V _{TR} =2.93 B; V _{DD} =15.5 B; I _{DD} <20 mKA	SOT23-5	RES • GND • RES • MR • VCC
DLR	MAX6319LHUK31	MAX	mrc	V _{TR} =3.08 B; V _{DD} =15.5 B; I _{DD} < 20 MKA	SOT23-5	RES • GND • RES • MR • VCC
	MAX6319LHUK44	MAX	mrc	V _{TR} =4.39 B; V _{DD} =15.5 B; I _{CC} <20 mKA	SOT23-5	RES • GND • RES • MR • VCC
DLT	MAX6316LUK26C	MAX	mrc	V _{TB} = 2.63 B; V _{DD} = 15.5 B; I _{CC} < 20 мкА	SOT23-5	RES • GND • MR • WDI • VCC
DLU	MAX6316LUK31C	MAX	mrc	V _{TR} =3.08 B; V _{DD} =15.5B; I _{CC} <20 мкА	SOT23-5	RES • GND • MR • WDI • VCC
	MAX6309UK27D1	MAX	mrc	V _{TB} =2.55B; V _{DD} =15.5B; I _{DC} <16 MKA	SOT23-5	RES • GND • MR • RST IN • VCC
	MAX9075EUK	MAX	cmp	R-R; V _{OSI} < ±8 MB; V _{CC} = 2.15.5 B; I _{CC} < 6.6 MKA	SOT23-5	OUT • GND • IN+• IN-• VCC
	MAX4430EUK	MAX	OA	V _{DD} = ±5 B; f _{BD} = 180МГц; V _{DS} < 5 мВ	SOT23-5	OUT • VEE • IN+• IN-• VCC
	MAX4431EUK	MAX	OA	V _{DD} = ±5 B; f _{BD} = 215MΓц; V _{DS} < 5 мВ	SOT23-5	OUT • VEE • IN+ • IN- • VCC
	MAX6316LUK26D	MAX	mrc	V _{TB} = 2.63 B; V _{DD} = 15.5 B; I _{CC} < 20 мкА	SOT23-5	RES • GND • MR • WDI • VCC
	MAX4626EUK	MAX	asw	SPST; R _{ON} < 12 OM; V _{DD} = 1.85.5 B	SOT23-5	COM • NO • GND • IN • V+
	MAX4627EUK	MAX	asw	SPST; R _{ON} < 12 OM; V _{DD} = 1.85.5 B	SOT23-5	COM • NC • GND • IN • V+
	MAX4291EUK	MAX	OA	B-R; V _{DD} = 1.85.5/±0.9±2.75 B; f _{BD} = 500 κΓu;	SOT23-5	IN+ • VEE • IN- • OUT • VCC
	Nagrativo isso proteina	100000		V _{DSI} < 2.5мВ	7 (2000) (2) (2) (2) (2)	STATE STREET,
DM A	MAX5360LEUK	MAX	DAC	6-разр.; I ² C; адрес: 0x60; V _{DD} =2.73.6В; V _{REF} =2В	SOT23-5	OUT • GND • VDD • SDA • SCL
DMN	MAX5380LEUK	MAX	DAC	8-разр.; I ² C; адрес: 0x60; V ₀₀ =2.73.6В; V _{BEF} =2В	SOT23-5	OUT • GND • VDD • SDA • SCL
DMO	MAX5360PEUK	MAX	DAC	6-разр.; I ² C; адрес: 0x66; V _{DD} =2.73.6В; V _{BEF} =2В	SOT23-5	OUT • GND • VDD • SDA • SCL
DMP	MAX5380PEUK	MAX	DAC	8-разр.; РС; адрес: 0x66; V _{DD} =2.73.6В; V _{BEF} =2В	SOT23-5	OUT • GND • VDD • SDA • SCL
DMQ	MAX5361PEUK	MAX	DAC	6-разр.; I ² C; адрес: 0x66; V ₀₀ =4.55.5В; V _{BEF} =4В	SOT23-5	OUT • GND • VDD • SDA • SCL
DMR	MAX5381PEUK	MAX	DAC	8-разр.; I ² C; адрес: 0x66; V ₀₀ =4.55.5В; V _{BEF} =4В	SOT23-5	OUT • GND • VDD • SDA • SCL
DMS	MAX5362PEUK	MAX	DAC	6-разр.; I ² C; адрес: 0x66; V _{DD} =2.75.5В; V _{BEF} =0.9xV _{DD}	SOT23-5	OUT • GND • VDD • SDA • SCL
DMT	MAX5382PEUK	MAX	DAC	8-pasp.; I ² C; appec: 0x66; V _{DD} =2.75.5B; V _{BEE} =0.9xV _{DD}	SOT23-5	OUT • GND • VDD • SDA • SCL
DMU	MAX5361LEUK	MAX	DAC	6-разр.; I ² C; адрес: 0x60; V ₀₀ =4.55.5В; V _{BEF} =4В	SOT23-5	OUT • GND • VDD • SDA • SCL
DMV	MAX5381LEUK	MAX	DAC	8-разр.; I ² C; адрес: 0x60; V _{DD} =4.55.5B; V _{REF} =4B	SOT23-5	OUT • GND • VDD • SDA • SCL
ADM N	MAX5362LEUK	MAX	DAC	6-разр., I ² C; адрес: 0x60; V _{DD} =2.75.5B; V _{BEF} =0.9xV _{DD}	SOT23-5	OUT • GND • VDD • SDA • SCL
DMX	MAX5382LEUK	MAX	DAC	8-pasp.; I ² C; agpec: 0x60; V _{DD} =2.75.5B; V _{REF} =0.9xV _{DD}	SOT23-5	OUT • GND • VDD • SDA • SCL
ADMY	MAX5360MEUK	MAX	DAC	6-разр.; I°C; адрес: 0x62; V _{DD} =2.73.6В; V _{BEE} =2В	SOT23-5	OUT • GND • VDD • SDA • SCL
DMZ	MAX5380MEUK	MAX	DAC	8-разр.; I ² C; адрес: 0x62; V ₀₀ =2.73.6В; V _{REF} =2В	SOT23-5	OUT • GND • VDD • SDA • SCL
DNA	MAX5361MEUK	MAX	DAC	6-разр.; I ² C; адрес: 0x62; V _{DD} =4.55.5В; V _{BEE} =4В	SOT23-5	OUT • GND • VDD • SDA • SCL
DNB	MAX5381MEUK	MAX	DAC	8-разр.; I ² C; адрес: 0x62; V _{DD} =4.55.5В; V _{BFE} =4В	SOT23-5	OUT • GND • VDD • SDA • SCL
DNC	MAX5362MEUK	MAX	DAC	6-разр., I ² C; адрес: 0x62; V _{DD} =2.75.5B; V _{BEE} =0.9xV _{DD}	SOT23-5	OUT • GND • VDD • SDA • SCL
DND	MAX5382MEUK	MAX	DAC	8-разр.; I ² C; адрес: 0x62; V ₀₀ =2.75.5B; V ₀₀ = 0.9 x V ₀₀	SOT23-5	OUT • GND • VDD • SDA • SCL
DNE	MAX5360NEUK	MAX	DAC	6-разр.; I ² C; адрес: 0x64; V _{DD} =2.73.6B; V _{REF} =2B	SOT23-5	OUT • GND • VDD • SDA • SCL
ADNF	MAX5380NEUK	MAX	DAC	8-разр.; I ² C; адрес: 0x64; V _{DD} =2.73.6B; V _{REF} =2B	SOT23-5	OUT • GND • VDD • SDA • SCL
ADNG	MAX5361NEUK	MAX	DAC	6-разр.; I ² C; адрес: 0x64; V ₀₀ =4.55.5В; V _{8FF} =4В	SOT23-5	OUT • GND • VDD • SDA • SCL
DNH	MAX5381NEUK	MAX	DAC	8-разр.; I ² C; адрес: 0x64; V _{DO} =4.55.5B; V _{BEF} =4B	SOT23-5	OUT • GND • VDD • SDA • SCL





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5
ADNI	MAX5362NEUK	MAX	DAC	6-разр.; I ² C; адрес: 0x64; V ₀₀ =2.75.5 В; V _{BEE} =0.9 x V _{DD}	SOT23-5	OUT • GND • VDD • SDA • SCL
LNDA	MAX5382NEUK	MAX	DAC	8-разр.; I ² C; адрес: 0x64; V _{DD} =2.75.5 В; V _{REF} =0.9 x V _{DD}	SOT23-5	OUT • GND • VDD • SDA • SCL
DNP	MAX4400AUK	MAX	OA	R-R; V _{DD} = 2.55.5 B; f _{BD} = 800 κΓιι; V _{DSI} < 5.5 мB	SOT23-5	IN+ • VSS • IN- • OUT • VDD
ADNR	MAX6316LUK44C	MAX	mrc	V ₁₈ =4.39B; V ₀₀ =15.5B; I ₀₀ <20 mKA	SOT23-5	RES • GND • MR • WDI • VCC
DNS	MAX6318LHUK26	MAX	mrc	V _{TB} =2.63B; V _{DD} =15.5B; I _{CC} <20 mKA	SOT23-5	RES • GND • RES • WDI • VCC
ADNT	MAX6509CAUK	MAX	tempsw	V _{CC} = 2.75.5 В; Т _{тн} = -40+125°С; I _{CC} < 165 мкА	SOT23-5	SET • GND • OUT • HYST • VCC
DNU	MAX6509HAUK	MAX	tempsw	V _{CC} = 2.75.5 В; Т _{тн} = -40+125°С; I _{CC} < 165 мкА	SOT23-5	SET • GND • OUT • HYST • VCC
NV	MAX9040AEUK	MAX	cmp+vref	R-R; V _{DSI} < ±7 MB; V _{CC} = 2.55.5 B; V _{REF} = 2.048 B; I _{CC} <72 MKA	SOT23-5	OUT • VEE • IN+ • REF • VCC
DNW	MAX9050AEUK	MAX	cmp+vref	R-R; V_{DSI} < ±7 MB; V_{CC} = 2.75.5 B; V_{REF} = 2.500 B; I_{CC} < 72 MKA	SOT23-5	OUT • VEE • IN+ • REF • VCC
ADNX	MAX9040BEUK	MAX	cmp+vref	$R-R$; $V_{DSI} < \pm 7 \text{ MB}$; $V_{CC} = 2.55.5 \text{ B}$; $V_{REF} = 2.048 \text{ B}$; $I_{CC} < 72 \text{ MKA}$	SOT23-5	OUT • VEE • IN+ • REF • VCC
DNY	MAX9050BEUK	MAX	cmp+vref	R -R; V_{DSI} < ± 7 MB; V_{CC} = 2.75.5 B; V_{REF} = 2.500 B; I_{CC} < 72 MKA	SOT23-5	OUT • VEE • IN+ • REF • VCC
	MAX4321EUK	MAX	OA	R-R; V_{DD} = 2.46.5/±1.2±3.25B; f_{BD} = 5 MFu; V_{OSI} < 3.5 mB	SOT23-5	CUT ◆VCC ◆IN+ ◆IN- ◆VEE
	MAX4645EUK	MAX	asw	SPST; R _{ON} < 3 O _M ; V _{DD} = 1.85.5 B	SOT23-5	COM • NO • GND • IN • V+
ADOC	MAX4646EUK	MAX	asw	SPST; R _{ON} < 3 Om; V _{DD} = 1.85.5 B	SOT23-5	COM • NC • GND • IN • V+
4DOD	MAX6320PUK26C	MAX	mrc	V _{TR} = 2.63B; V _{DD} = 15.5B; I _{CC} < 20 mKA	SOT23-5	RES • GND • MR • WDI • VCC
ADOE	MAX4568EUK	MAX	asw	SPST; R _{ON} < 75 OM; V _{DD} = 1.812B	SOT23-5	COM • NO • GND • IN • V+
DOF	MAX4569EUK	MAX	asw	SPST; R _{ON} < 75 O _M ; V _{DO} = 1.812B	SOT23-5	COM • NC • GND • IN • V+
ADOG	MAX4376TAUK	MAX	CSA	V _{DO} = 328 B; Gain = 20; I _{CC} < 2.2 mA	SOT23-5	OUT • GND • VCC • RS+ • RS-
HOOL	MAX4376FAUK	MAX	CSA	V ₀₀ = 328 В; Gain = 50; I _{CC} < 2.2 мА	SOT23-5	OUT • GND • VCC • RS+ • RS-
ADOI	MAX4376HAUK	MAX	CSA	V _{DO} = 328 B; Gain = 100; I _{CC} < 2.2 мА	SOT23-5	OUT • GND • VCC • RS+ • RS-
ADOJ	MAX9031AUK	MAX	стр	R-R; V _{DSI} < ±5 mB; V _{DD} = 2.55.5 B; I _{DD} < 55 mkA	SOT23-5	IN+ • VSS • IN- • OUT • VDD
ADOK	MAX6316LUK46C	MAX	mrc	V _{TR} =4.63B; V _{DD} =15.5B; I _{CC} < 20 MKA	SOT23-5	RES • GND • MR • WDI • VCC
ADOL	MAX4412EUK	MAX	OA	R-R; V _{DD} = 2.75.5 B; f _{BD} = 500 MΓц; V _{DSI} < 9 мВ	SOT23-5	OUT • VEE • IN+• IN- • VCC
DOM	MAX6319MHUK29	MAX	mrc	V _{TB} = 2.93B; V _{DD} = 15.5B; I _{CC} < 20 MKA	SOT23-5	RES • GND • RES • MR • VCC
ADOP	MAX6319MHUK46	MAX	mrc	V _{TB} = 4.63B; V _{DD} = 15.5B; I _{CC} < 20 MKA	SOT23-5	RES • GND • RES • MR • VCC
ADOR	MAX9100EUK	MAX	стр	R-R; V _{DSI} < ±20 mB; V _{DC} = 15.5B; I _{DC} < 13 mkA	SOT23-5	OUT • GND • IN+ • IN- • VCC
ADOS	MAX9101EUK	MAX	стр	V _{OSI} < ±20 mB; V _{CC} = 15.5 B; I _{CC} < 13 mkA	SOT23-5	OUT • GND • IN+ • IN- • VCC
	MAX4434EUK	MAX	OA	V _{DD} = ±5 B; f _{RD} = 150 MFu; Gain = 1; V _{DSI} < 3.5 MB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
	MAX4435EUK	MAX	OA	V _{DO} = ±5 B; f _{BD} = 150 MFu; Gain = 5; V _{DSI} < 3.5 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ADOV	MAX4452EUK	MAX	OA	R-R; V _{DD} = 2.75.25 B; f _{BD} = 200 MFu; V _{DS} < 12 MB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ADOW	MAX4352EUK	MAX	OA	R-R; V _{DO} = 2.75.25 B; f _{BD} = 80 MFu; V _{OSI} < 12 MB	SOT23-5	OUT • VEE • IN+• IN- • VCC
ADOX	MAX1735EUK25	MAX	reg	LDO; V _{IN} = -2.56.5B; V _{OUT} = -2.5/-1.255.5B; I _{OUT} = 200 mA	SOT23-5	GND • IN • SHDN • SET • OUT
4DOY	MAX1735EUK30	MAX	reg	LDO; V _{IN} = -2.56.5B; V _{DUT} = -3.0/-1.255.5B; I _{DUT} = 200 mA	SOT23-5	GND • IN • SHDN • SET • OUT
	MAX1735EUK50	MAX	reg	LDO; V _{IN} = -2.56.5 B; V _{OUT} = -5.0/-1.255.5 B; I _{OUT} = 200 mA	SOT23-5	GND • IN • SHDN • SET • OUT
	MAX6321HPUK25	MAX	mrc	$V_{TR} = 2.463 \text{ B}; V_{DO} = 15.5 \text{ B}; I_{CC} < 20 \text{ mKA}$	SOT23-5	RES • GND • RES • WDI • VCC
DPD	MAX9021AUK	MAX	стр	R-R; V _{DSI} < ±8 mB; V _{DD} = 2.55.5 B; I _{DD} < 5 mrA	SOT23-5	IN+ • VSS • IN- • OUT • VDD
DPE	MAX4484AUK	MAX	OA	R-R; V _{DD} =2.75.5 B; f _{BD} =7 MFu; V _{DSI} <9 MB	SOT23-5	IN+ • VSS • IN- • OUT • VDD
DPF	MAX6317HUK46B	MAX	mrc	V _{TR} = 4.63 B; V _{DD} = 15.5 B; I _{CC} < 20 мкА	SOT23-5	RES • GND • MR • WDI • VCC
ADPG	MAX4493AUK	MAX	OA	R-R; V _{DD} = ±2.25±5.5 B; f _{BD} = 5 MΓц; V _{DSI} < 10 мB	SOT23-5	IN+•VEE•IN-•OUT•VCC
	MAX4470EUK	MAX	OA	R-R; V_{DD} =1.85.5 B; f_{BD} =9 κΓц; I_{CC} < 1.2 мкA; V_{OSI} <7 мB	SOT23-5	IN+•VSS•IN-•OUT•VDD
ADPI	MAX4464EUK	MAX	OA	R -R; V_{DD} = 1.85.5 B; f_{BD} = 40 κΓιμ; I_{CC} < 1.2 мκA; V_{DSI} < 7 мB	SOT23-5	IN+•VSS•IN-•OUT•VDD
ADP.J	MAX4480AUK	MAX	OA	R-R; V _{DD} =2.55.5 B; I _{DD} <100 mKA; V _{DSI} <5.5 mB	SOT23-5	IN+ • VSS • IN- • OUT • VDD





ADPO MA: ADPR MA: ADPR MA: ADPR MA: ADPV MA: ADPV MA: ADPV MA: ADPW MA: ADPW MA: ADQG MA: ADQ	AXSE23VUK AXSE21UIK AXSE22VUK AXSE22VUK AXSE22VUK AXSE25VUK AXSE25VUK AXSE35VUK AXSE35	MAX	mrc+wdt mrc+wdt mrc+wdt mrc+wdt mrc-wdt mrc-wdt mrc mrc mrc dede dede dede dede dede dede dede de	$\begin{aligned} &V_{IR}\!=\!1.58B,V_{OD}\!=\!1255B,I_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!4.63B,V_{DD}\!=\!1255B,I_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!3.08B,V_{DD}\!=\!1255B,I_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!2.38B,V_{DD}\!=\!1255B,I_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!3.08B,V_{DD}\!=\!1255B,I_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!3.08B,V_{DD}\!=\!1255B,I_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!3.08B,V_{DD}\!=\!1255B,I_{CC}\!<\!50\text{MeA} \\ &V_{IR}\!=\!2.39B,V_{IR}\!=\!1.67B,V_{DD}\!=\!1255B,I_{CC}\!<\!50\text{MeA} \\ &V_{IR}\!=\!2.93B,V_{IR}\!=\!1.67B,V_{DD}\!=\!1255B,I_{CC}\!<\!50\text{MeA} \\ &V_{IR}\!=\!2.93B,V_{DD}\!=\!1.58B,V_{DD}\!=\!1255B,I_{CD}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.856B,V_{DD}\!=\!255B,I_{DD}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.856B,V_{DD}\!=\!276B,I_{DD}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.856B,V_{DD}\!=\!278B,I_{DD}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.856B,V_{DD}\!=\!3.3B,I_{DD}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.856B,V_{DD}\!=\!3.3B,I_{DD}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.856B,V_{DD}\!=\!3.3B,I_{DD}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.856B,V_{DD}\!=\!3.3B,I_{DD}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.856B,V_{DD}\!=\!3.2B,I_{DD}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.856B,V_{DD}\!=\!3.2B,I_{DD}\!=\!150\text{MeA} \\ &V_{IR}\!=\!2.32B,V_{DD}\!=\!1255B,I_{DD}\!=\!1255B,I_{DD}\!=\!1256B,I_{DD}\!=\!1266B,I_{DD}\!=\!1266$	TSOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 SOT23-5 TSOT23-5 SOT23-5 SOT23-5 SOT23-5	RES - GND - MR - WDI - VCC RES - GND - MR - WDI - VCC RES - GND - MR - WDI - VCC RES - GND - MR - WDI - VCC RES - GND - MR - WDI - VCC RES - GND - RES - MR - VCC RES - GND - MR - VCC2 - VCC1 RST - GND - MR - VCC2 - VCC1 RST - GND - MR - VCC2 - VCC1 RST - GND - MR - VCC2 - VCC1 BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX RST - GND - MR - VCC2 - VCC1 RST - GND - MR - VCC2 - VCC1 RST - GND - MR - VCC2 - VCC1 RST - GND - MR - VCC2 - VCC1 RES - GND - MR - VCC2 - VCC1 RES - GND - MR - VCC2 - VCC1 RES - GND - RR - VDI - VCC
ADPR MAA ADPS MAA ADPS MAA ADPY MAA ADPV MAA ADPV MAA ADPV MAA ADQF MAA ADQG MAA	AXS822WUK AXS822WUK AXS852TWUK AXS852TWUK AXS8552TWUK AXS8552TWUK AXS8552TWUK AXS8552TWUK AXS8552TWUK AXS8552TWUK AXS8552TWUK AXS8552TWUK AXS854TWUK AXS854TWUK AXS854TWUK AXS854TWUK AXS855TWUK AXS856TUKP125 AXS855TWUK AXS865TWUK AXS8685TWUK AXS8687TWZ69	MAX	mrc+wdt mrc+wdt mrc-wdt mrc mrc mrc dede dede dede dede dede dede dede mrc dede rempsw mrc+wdt mrc mrc+wdt mrc dege feg	$\begin{split} &V_{TR}\!=\!1.67B,V_{OD}\!=\!1255B,t_{CC}\!<\!30\text{MeA} \\ &V_{TR}\!=\!2.32B,V_{DD}\!=\!1255B,t_{CC}\!<\!30\text{MeA} \\ &V_{TR}\!=\!3.08B,V_{DD}\!=\!1255B,t_{CC}\!<\!30\text{MeA} \\ &V_{TR}\!=\!3.08B,V_{DD}\!=\!1255B,t_{CC}\!<\!30\text{MeA} \\ &V_{TR}\!=\!3.08B,V_{DD}\!=\!1255B,t_{CC}\!<\!50\text{MeA} \\ &V_{TR}\!=\!2.93B,V_{TR}\!=\!1.58B,V_{OD}\!=\!1255B,t_{CC}\!<\!50\text{MeA} \\ &V_{TR}\!=\!2.93B,V_{TR}\!=\!1.58B,V_{OD}\!=\!1255B,t_{CC}\!<\!50\text{MeA} \\ &V_{TR}\!=\!2.73B,V_{TR}\!=\!1.67B,V_{DD}\!=\!1255B,t_{CC}\!<\!50\text{MeA} \\ &V_{TR}\!=\!0.856B,V_{DDT}\!=\!255B,t_{DUT}\!=\!150\text{MeA} \\ &V_{N}\!=\!0.856B,V_{DDT}\!=\!255B,t_{DUT}\!=\!150\text{MeA} \\ &V_{N}\!=\!0.856B,V_{DUT}\!=\!255B,t_{DUT}\!=\!150\text{MeA} \\ &V_{N}\!=\!0.856B,V_{DUT}\!=\!3.3B,t_{DUT}\!=\!150\text{MeA} \\ &V_{N}\!=\!0.856B,V_{DUT}\!=\!3.3B,t_{DUT}\!=\!150\text{MeA} \\ &V_{N}\!=\!0.856B,V_{DUT}\!=\!3.3B,t_{DUT}\!=\!150\text{MeA} \\ &V_{N}\!=\!0.856B,V_{DUT}\!=\!3.5B,t_{DUT}\!=\!150\text{MeA} \\ &V_{N}\!=\!0.856B,V_{DUT}\!=\!3.5B,t_{DUT}\!=\!150\text{MeA} \\ &V_{N}\!=\!0.856B,V_{DUT}\!=\!5B,t_{DUT}\!=\!150\text{MeA} \\ &V_{N}\!=\!0.856B,V_{DUT}\!=\!5B,t_{DUT}\!=\!150\text{MeA} \\ &V_{N}\!=\!2.3B,V_{DD}\!=\!1.255B,t_{CC}\!<\!30\text{MemA} \\ &V_{N}\!=\!2.3B,V_{DD}\!=\!1.255B,t_{CC}\!<\!30\text{MemA} \\ &V_{N}\!=\!2.3B,V_{DD}\!=\!1.255B,t_{CC}\!<\!30\text{MemA} \\ &V_{N}\!=\!2.3B,V_{DD}\!=\!1.255B,t_{CC}\!<\!30\text{MemA} \\ &V_{N}\!=\!2.1B,V_{DD}\!=\!1.255B,t_{CC}\!<\!30\text{MemA} \\ &V_{N}\!=\!2.1B,V_{DD}\!=\!1.255B,t_{CC}\!=\!30\text{MeA} \\ &V_{N}\!=\!2.1B,V_{DD}\!=\!1.255B,t_{CC}\!=\!30\text{MeA} \\ &V_{N}\!=\!2.06B,V_{DD}\!=\!25B,t_{DUT}\!=\!150\text{MeA} \\ &V_{DD}\!=\!265B,V_{DDT}\!=\!255B,t_{DDT}\!=\!150\text{MeA} \\ &V_{DD}\!=\!265B,V_{DDT}\!=\!255B,t_{DDT}\!=\!150\text{MeA} \\ &V_{DD}\!=\!265B,V_{DDT}\!=\!255B,t_{DDT}\!=\!150\text{MeA} \\ &V_{DD}\!=\!265B,V_{DDT}\!=\!255B,t_{DDT}\!=\!150\text{MeA} \\ &V_{DD}\!=\!265B,V_{DDT}\!=\!255B,t_{DDT}\!=\!150\text{MeA} \\ &V_{DD}\!=\!265B,V_{DDT}\!=\!265B,t_{DDT}\!=\!265B,t_{DDT}\!=\!150\text{MeA} \\ &V_{DD}\!=\!265B,$	SOT23-5 SOT23-5 SOT23-5 SOT23-5 SOT23-5 SOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 SOT23-5 SOT23-5 SOT23-5	RES - GND - MR - WDI - VCC RES - GND - RES - WDI - VCC RES - GND - RES - WDI - VCC RES - GND - RES - WDI - VCC RST - GND - MR - VCC2 - VCC1 RST - GND - MR - VCC2 - VCC1 BATT - GND - MR - VCC2 - VCC1 BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX GATT - GND - FB - CND - CN
ADPS MAA ADPT MAAADPT MAA ADPT	AX6824ZUK AX6826ZTUK AX6836ZTWUK AX635SZWUK AX635SZWUK AX635SZWUK AX635SZWUK AX722EZK AX1724EZK27 AX1724EZK30 AX6854ZUK AX6825ZUK5 AX6865ZUK5 AX6867ZK25 AX6867ZK25 AX6867ZK25	MAX MAX MAX MAX MAX MAX MAX MAX MAX MAX	mrc+wdt mrc+wdt mrc mrc mrc dede dede dede dede dede dede dede de	$\begin{split} &V_{IR}\!=\!2.32B,V_{OD}\!=\!1255B,t_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!3.08B,V_{DD}\!=\!1255B,t_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!3.08B,V_{ID2}\!=\!1.67B,V_{OD}\!=\!1255B,t_{CC}\!<\!50\text{MeA} \\ &V_{IR}\!=\!2.93B,V_{ID2}\!=\!1.67B,V_{OD}\!=\!1255B,t_{CC}\!<\!50\text{MeA} \\ &V_{IR}\!=\!2.93B,V_{ID2}\!=\!1.67B,V_{OD}\!=\!1255B,t_{CC}\!<\!50\text{MeA} \\ &V_{IR}\!=\!2.78B,V_{ID2}\!=\!1.67B,V_{OD}\!=\!1255B,t_{CC}\!<\!50\text{MeA} \\ &V_{IR}\!=\!0.855B,V_{OUT}\!=\!255B,t_{OUT}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.855B,V_{OUT}\!=\!255B,t_{OUT}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.855B,V_{OUT}\!=\!3.5B,t_{OUT}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.855B,V_{OUT}\!=\!3.3B,t_{OUT}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.855B,V_{OUT}\!=\!3.3B,t_{OUT}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.855B,V_{OUT}\!=\!3.5B,t_{OUT}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.855B,V_{OUT}\!=\!3.5B,t_{OUT}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.855B,V_{OUT}\!=\!5.5B,t_{OUT}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.855B,V_{OUT}\!=\!5.5B,t_{OUT}\!=\!150\text{MeA} \\ &V_{IR}\!=\!0.855B,V_{OUT}\!=\!5.5B,t_{OUT}\!=\!150\text{MeA} \\ &V_{IR}\!=\!2.3B,V_{OD}\!=\!1255B,t_{OUT}\!=\!150\text{MeA} \\ &V_{IR}\!=\!2.3B,V_{OD}\!=\!1255B,t_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!2.3B,V_{OD}\!=\!1255B,t_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!2.2B,V_{OD}\!=\!1255B,t_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!2.2B,V_{OD}\!=\!1255B,t_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!25B,V_{OUT}\!=\!2.5B,t_{OUT}\!=\!50\text{MeA} \\ &V_{IR}\!=\!25B,V_{OUT}\!=\!2.5B,t_{OUT}\!=\!2.5B,t_{OUT}\!=\!50\text{MeA} \\ &V_{IR}\!=\!25B,V_{OUT}\!=\!2.5B,t_{OUT}\!=\!50\text{MeA} \\ &V_{IR}\!=\!25B,V_{OUT}\!=\!2.5B,t_{OUT}\!=\!2.5B,t_{OUT}\!=\!3.5B,t_{OUT}\!=\!3.5B,t_{OUT}\!=\!3.5B,t_{OUT}\!=\!3.5B,t_{OUT}\!=\!3.5B,t_{OUT}\!=\!3.5B,t_{OUT}\!=\!3.5B,t_{OUT$	SOT23-5 SOT23-5 SOT23-5 SOT23-5 SOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 SOT23-5 SOT23-5 SOT23-5	RES - GND - RES - WDI - VCC RES - GND - RES - MR - VCC RST - GND - MR - VCC2 - VCC1 RST - GND - MR - VCC2 - VCC1 RST - GND - MR - VCC2 - VCC1 BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX GATT - GND - FB - OUT - LX GATT - GND - FB - OUT - LX GATT - GND - FB - OUT - LX RST - GND - FB - OUT - LX GATT - GND - FB - OUT - LX RST - GND - FB - OUT - LX GRD - GND - FB - OUT - LX RST - GND - FB - OUT - LX GRD - GND - FB - OUT - LX RST - GND - FB - CND - LX RST - GND - FB - CND - LX RST - GND - FB - CND - LX RST - GND - FB - CND - LX RST - GND - FB - CND - LX RST - GND - FB - CND - LX RST - GND - FB - CND - LX RST - GND - CND - CND - LX RST - GND -
ADPT MAA ADPW MAA ADPW MAA ADPW MAA ADPW MAA ADPW MAA ADGG MAA ADG	AX6825TUK AX6352TWUK AX6353SVUK AX6354UWUK AX1725EZK AX1724EZK27 AX1724EZK27 AX1724EZK30	MAX	mrc+wdt mrc mrc mrc dddc dddc dddc dddc dddc dd	$\begin{split} &V_{IR}\!=\!3.08B,V_{DO}\!=\!1255B,t_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!3.08B,V_{IR}\!=\!167B,V_{DO}\!=\!1255B,t_{CC}\!<\!50\text{MeA} \\ &V_{IR}\!=\!2.30B,V_{IR}\!=\!158B,V_{DO}\!=\!1255B,t_{CC}\!<\!50\text{MeA} \\ &V_{IR}\!=\!2.93B,V_{IR}\!=\!167B,V_{DO}\!=\!1255B,t_{CC}\!<\!50\text{MeA} \\ &V_{IR}\!=\!2.78B,V_{IR}\!=\!167B,V_{DO}\!=\!1255B,t_{CC}\!<\!50\text{MeA} \\ &V_{IR}\!=\!2.78B,V_{IR}\!=\!167B,V_{DO}\!=\!1255B,t_{CO}\!=\!150\text{MA} \\ &V_{IR}\!=\!0.855B,V_{DUI}\!=\!255B,t_{DUI}\!=\!150\text{MA} \\ &V_{IR}\!=\!0.855B,V_{DUI}\!=\!255B,t_{DUI}\!=\!150\text{MA} \\ &V_{IR}\!=\!0.855B,V_{DUI}\!=\!3.08B,t_{DUI}\!=\!150\text{MA} \\ &V_{IR}\!=\!0.855B,V_{DUI}\!=\!3.08B,V_{DO}\!=\!1255B,t_{DUI}\!=\!150\text{MA} \\ &V_{IR}\!=\!6.35B,V_{DUI}\!=\!3.08B,V_{DO}\!=\!1255B,t_{DUI}\!=\!150\text{MA} \\ &V_{IR}\!=\!2.35B,V_{DUI}\!=\!5.08L_{DUI}\!=\!150\text{MA} \\ &V_{CC}\!=\!2.755B,T_{DII}\!=\!125C,t_{DC}\!<\!65\text{MeA} \\ &V_{CC}\!=\!2.755B,T_{DII}\!=\!125C,t_{DC}\!<\!65\text{MeA} \\ &V_{IR}\!=\!2.32B,V_{DO}\!=\!1255B,t_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!2.32B,V_{DO}\!=\!1255B,t_{CC}\!<\!30\text{MeA} \\ &V_{IR}\!=\!2.23B,V_{DO}\!=\!1255B,t_{CC}\!<\!30\text{MeA} \\ &U_{DO}\!=\!0.1252B,t_{DOI}\!=\!1255B,t_{DC}\!=\!50\text{MeA} \\ &U_{DO}\!=\!0.1252B,t_{DOI}\!=\!1255B,t_{DC}\!=\!50\text{MeA} \\ &U_{DO}\!=\!0.1252B,t_{DOI}\!=\!1252B,t_{DOI}\!=\!150\text{MA} \\ &U_{DO}\!=\!0.252B,t_{DOI}\!=\!1252B,t_{DOI}\!=\!150\text{MA} \\ &U_{DO}\!=\!0.252B,t_{DOI}\!=\!1252B,t_{DOI}\!=\!150\text{MA} \\ &U_{DO}\!=\!0.252B,t_{DOI}\!=\!1252B,t_{DOI}\!=$	SOT23-5 SOT23-5 SOT23-5 SOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 SOT23-5 SOT23-5 SOT23-5 SOT23-5 SOT23-5	RES - GND - RES - MR - VCC RST - GND - MR - VCC2 - VCC1 RST - GND - MR - VCC2 - VCC1 RST - GND - MR - VCC2 - VCC1 RST - GND - MR - VCC2 - VCC1 BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX RST - GND - MR - VCC2 - VCC1 BATT - GND - MR - VCC2 - VCC1 RST - GND - MR - VCC2 - VCC1 RES - GND - HYST - VCC - TOVER RES - GND - MR - WDI - VCC RES - GND - RES - WDI - VCC
ADPU MAA ADPW MAA ADP	AX6352TWUK AX6363SWUK AX6353FUMUK AX6353FUMUK AX1722EZK AX1724EZK27 AX1724EZK27 AX1724EZK30 AX1724EZK3	MAX	mrc mrc dede dede dede dede dede dede dede mrc dede mrc dede mrc dede tempsw mrc+wdt reg reg	$\begin{split} &V_{TR} = 3.08B, V_{TR} = 1.67B, V_{DO} = 1.25.5B; \\ &V_{CC} \leq 50 \text{msA} \\ &V_{TR} = 2.93B, V_{TR} = 1.58B, V_{DO} = 1.25.5B; \\ &V_{CC} \leq 50 \text{msA} \\ &V_{TR} = 2.78B, V_{DR} = 1.67B, V_{DO} = 1.25.5B; \\ &V_{CC} \leq 50 \text{msA} \\ &V_{N} = 0.85.5B, V_{OUT} = 25.5B, I_{OUT} = 150 \text{msA} \\ &V_{N} = 0.85.5B, V_{DUT} = 25.5B, I_{OUT} = 150 \text{msA} \\ &V_{N} = 0.85.5B, V_{DUT} = 2.0.5.18, I_{OUT} = 150 \text{msA} \\ &V_{N} = 0.85.5B, V_{DUT} = 2.0.5.18, I_{OUT} = 150 \text{msA} \\ &V_{N} = 0.85.5B, V_{DUT} = 3.00B, V_{DUT} = 150 \text{msA} \\ &V_{N} = 0.85.5B, V_{DUT} = 3.00B, V_{DD} = 125.5B, I_{CC} \leq 50 \text{msA} \\ &V_{N} = 0.85.5B, V_{DUT} = 50.00B, V_{DD} = 125.5B, I_{CC} \leq 50 \text{msA} \\ &V_{N} = 2.00B, V_{DD} = 125.5B, I_{CUT} = 150 \text{msA} \\ &V_{CT} = 2.76.5B, T_{TR} = 4125 C, I_{CC} \leq 65 \text{msA} \\ &V_{TR} = 2.92B, V_{DD} = 125.5B, I_{CC} \leq 30 \text{msA} \\ &V_{N} = 2.9850B, V_{DD} = 2.5.5B, I_{CC} \leq 50 \text{msA} \\ &V_{N} = 2.9850B, V_{DD} = 2.5.5B, I_{CC} \leq 50 \text{msA} \\ &V_{N} = 2.9850B, V_{DD} = 2.5.5B, I_{CD} = 150 \text{msA} \\ &V_{DC} = 250B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 \text{msA} \\ &V_{DC} = 2.5.65B, V_{DD} = 2.5.5B, I_{DD} = 150 $	SOT23-5 SOT23-5 SOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 SOT23-5 SOT23-5 SOT23-5 SOT23-5	RST = GND = MR = VCC2 = VCC1 RST = GND = MR = VCC2 = VCC1 RST = GND = MR = VCC2 = VCC1 BATT = GND = FR = OUT = LX BATT = GND = FR = OUT = LX BATT = GND = FR = OUT = LX BATT = GND = FR = OUT = LX BATT = GND = FR = OUT = LX BATT = GND = FR = OUT = LX BATT = GND = FR = OUT = LX BATT = GND = FR = OUT = LX BATT = GND = FR = OUT = LX BATT = GND = FR = OUT = LX RST = GND = MR = VCC2 = VCC1 RST = GND = GND = FR = OUT = LX RST = GND = GND = FR = OUT = LX RST = GND = GND = FR = OUT = VCC RES = GND = FR = OUT = VCC RES = GND = FR = S = OUT = VCC RES = GND = FR = S = OUT = VCC
ADPV MAAADPV MAAAADPV MAAAADPV MAAAADPV MAAADPV MAAADPV MAAADPV MAAAADPV MAAADPV MAAAADPV MAAAAADPV MAAAAADPV MAAAAADPV MAAAAADPV MAAAAADPV MAAAAADPV MAAAAADPV MAAAADPV MAAAAADPV MAAAAAADPV MAAAAADPV MAAAAAAADPV MAAAAAAADPV MAAAAAADPV MAAAAAAADPV MAAAAAAAAADPV MAAAAAAADPV MAAAAAAAAAADPV MAAA	AX6353SVUK AX6354UWUK AX1722EZK AX1722EZK AX1724EZK3 AX1724EZK3 AX1724EZK3 AX1724EZK3 AX1724EZK3 AX1724EZK3 AX1724EZK3 AX6354UWK9 AX6561UWF0125 AX6825VUK AX68651ZK2 AX68657ZK29 AX6867ZK29	MAX	mrc mrc dede dede dede dede dede dede dede mrc dede mrc dede mrc+wdt reg reg	$\begin{aligned} & \{c_0 \le 50 \text{msA} \} \\ & V_{119} = 2.938, V_{102} = 1.58 \text{ B}; V_{00} = 125.58 \} \\ & \{c_0 \le 50 \text{msA} \} \\ & V_{119} = 2.788, V_{112} = 1.678, V_{00} = 125.58 \} \\ & \{c_0 \le 50 \text{msA} \} \\ & V_{11} = 0.85.58, V_{001} = 25.58, V_{001} = 150 \text{msA} \} \\ & V_{11} = 0.85.58, V_{001} = 25.58, V_{001} = 150 \text{msA} \} \\ & V_{11} = 0.85.58, V_{001} = 2.78, V_{001} = 150 \text{msA} \} \\ & V_{11} = 0.85.58, V_{001} = 2.78, V_{001} = 150 \text{msA} \} \\ & V_{11} = 0.85.58, V_{001} = 3.38, V_{001} = 150 \text{msA} \} \\ & V_{11} = 0.85.58, V_{001} = 3.38, V_{001} = 150 \text{msA} \} \\ & V_{11} = 0.85.58, V_{001} = 3.98, V_{001} = 1.25.58, C 50 \text{msA} \} \\ & V_{11} = 0.85.58, V_{001} = 50, V_{001} = 150 \text{msA} \} \\ & V_{12} = 2.328, V_{00} = 1.25.58, V_{001} = 150 \text{msA} \} \\ & V_{12} = 2.328, V_{001} = 2.5.58, V_{001} = 2.5.88, V_{001} = 150 \text{msA} \} \\ & V_{12} = 2.98, V_{001} = 1.25.58, V_{001} = 2.5.88, V_{001} = 150 \text{msA} \} \\ & V_{12} = 2.98, V_{001} = 1.25.58, V_{001} = 2.5.88, V_{001} = 150 \text{msA} \} \\ & V_{12} = 2.98, V_{001} = 1.25.58, V_{001} = 2.5.88, V_{001} = 150 \text{msA} \} \\ & V_{12} = 2.98, V_{001} = 1.25.58, V_{001} = 2.5.88, V_{001} = 150 \text{msA} \} \\ & V_{12} = 2.05.88, V_{001} = 2.5.88, V_{001} = 2.5.88, V_{001} = 150 \text{msA} \} \\ & V_{12} = 2.05.88, V_{001} = 2.5.88, V_{001} = 2.5.88, V_{001} = 150 \text{msA} \} \\ & V_{12} = 2.05.88, V_{001} = 2.5.88, V_{001} = 2.5.88, V_{001} = 150 \text{msA} \} \\ & V_{12} = 2.05.88, V_{001} = 2.5.88, V_{001} = 2.5.88, V_{001} = 150 \text{msA} \} $	SOT23-5 SOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 SOT23-5 SOT23-5 SOT23-5 SOT23-5 SOT23-5	RST • GND • MR • VCC2 • VCC1 RST • GND • MR • VCC2 • VCC1 BATT • GND • FB • OUT • LX BATT • GND • FB • OUT • LX BATT • GND • FB • OUT • LX BATT • GND • FB • OUT • LX BATT • GND • FB • OUT • LX BATT • GND • FB • OUT • LX GATT • GND • FB • OUT • LX GATT • GND • FB • OUT • LX GRD • GND • FB • OUT • LX GRD • GND • FB • OUT • LX GRD • GND • FB • OUT • LX GRD • GND • FB • OUT • LX GRD • GND • FB • OUT • LX GRD • GND • FB • OUT • LX GRD • GND • FB • OUT • LX GRD • GND • FB • OUT • LX GRD • GND • FB • OUT • LX
ADPW MAX ADGF MAX ADGG MAX ADGH MAX ADGJ MAX ADGJ MAX ADGJ MAX ADGL MAX ADGR MAX ADG	AX6354UWUK AX1723EZK AX1723EZK AX1724EZK27 AX1724EZK30 AX1724EZK30 AX1724EZK33 AX6354LTUK AX6601UKP125 AX6821ZUK AX6825YUK AX6825YUK AX6867ZK25 AX8667ZK29	MAX	mrc dedc dedc dedc dedc dedc dedc dedc d	$\begin{split} & \{ c_0 \le SO \text{MarA} \} \\ & V_{110} = 2.78 \text{B}, \ V_{100} = 1.67 \text{B}, \ V_{00} = 125.5 \text{B}, \ \\ & \{ c_0 \le SO \text{MarA} \} \\ & V_{N1} = 0.85.5 \text{B}, \ V_{011} = 25.5 \text{B}, \ t_{011} = 150 \text{MA} \\ & V_{N1} = 0.85.5 \text{B}, \ V_{011} = 25.5 \text{B}, \ t_{011} = 150 \text{MA} \\ & V_{N1} = 0.85.5 \text{B}, \ V_{011} = 2.7 \text{B}, \ t_{011} = 150 \text{MA} \\ & V_{N1} = 0.85.5 \text{B}, \ V_{011} = 3.0 \text{B}, \ t_{011} = 150 \text{MA} \\ & V_{N1} = 0.85.5 \text{B}, \ V_{011} = 3.0 \text{B}, \ t_{011} = 150 \text{MA} \\ & V_{N1} = 0.85.5 \text{B}, \ V_{011} = 3.0 \text{B}, \ t_{011} = 150 \text{MA} \\ & V_{N1} = 0.85.5 \text{B}, \ V_{011} = 3.0 \text{B}, \ t_{011} = 150 \text{MA} \\ & V_{N1} = 2.0 \text{B}, \ V_{011} = 5.5 \text{B}, \ t_{011} = 150 \text{MA} \\ & V_{N2} = 2.76.5 \text{B}, \ T_{N1} = 1.212 \text{C}, \ t_{012} \le S0 \text{MarA} \\ & V_{N2} = 2.2 \text{B}, V_{001} = 1.255 \text{B}, \ t_{022} \le S0 \text{MarA} \\ & U_{N2} = 2.9 \text{B}, V_{001} = 2.5 \text{B}, \ t_{021} = 150 \text{MA} \\ & U_{D}, V_{N1} = 2.56.5 \text{B}, \ V_{011} = 2.5 \text{B}, \ t_{011} = 150 \text{MA} \\ & U_{D}, V_{N2} = 2.56.5 \text{B}, \ V_{011} = 2.5 \text{B}, \ t_{011} = 150 \text{MA} \\ & U_{D}, V_{N1} = 2.56.5 \text{B}, V_{011} = 2.5 \text{B}, \ t_{011} = 150 \text{MA} \\ & U_{D}, V_{N1} = 2.56.5 \text{B}, V_{011} = 2.5 \text{B}, \ t_{011} = 150 \text{MA} \\ & U_{D}, V_{N1} = 2.56.5 \text{B}, V_{011} = 2.5 \text{B}, \ t_{011} = 150 \text{MA} \\ & U_{D}, V_{N1} = 2.56.5 \text{B}, V_{011} = 2.5 \text{B}, \ t_{011} = 150 \text{MA} \\ & U_{D}, V_{N1} = 2.56.5 \text{B}, V_{011} = 2.5 \text{B}, \ t_{011} = 150 \text{MA} \\ & U_{D}, V_{N1} = 2.56.5 \text{B}, V_{011} = 2.5 \text{B}, \ t_{011} = 150 \text{MA} \\ & U_{D}, V_{N1} = 2.56.5 \text{B}, V_{011} = 2.5 \text{B}, \ t_{011} = 150 \text{MA} \\ & U_{D}, V_{N1} = 2.56.5 \text{B}, V_{011} = 2.5 \text{B}, V_{011} = 150 \text{MA} \\ & U_{D}, V_{N1} = 2.56.5 \text{B}, V_{011} = 2.5 \text{B}, V_{011} = 150 \text{MA} \\ & U_{D}, V_{N1} = 2.56.5 \text{B}, V_{011} = 2.5 \text{B}, V_{011} = 150 \text{MA} \\ & U_{D}, V_{N1} = 2.56.5 \text{B}, V_{011} = 2.5 \text{B}, V_{012} = 2$	SOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 SOT23-5 SOT23-5 SOT23-5 SOT23-5	RST - GND - MR - VCC2 - VCC1 BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - MR - VCC2 - VCC1 BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX RES - GND - MR - VCC2 - VCC1 RES - GND - MR - VCC2 - VCC2 RES - GND - MR - VCC2 - VCC2 RES - GND - MR - VCC3 - VCC2 RES - GND - RES - VWDI - VCC
ADQF MAAADQC MAAADQC MAAADQC MAAAADQC MAAAADQC MAAAADQC MAAAADQC MAAAADQC MAAAADQC MAAAADQC MAAAAADQC MAAAAAAAAAAAAAAAAAAAAAAAAAAAAAAAAAAAA	AX1722EZK AX1723EZK AX1724EZK27 AX1724EZK30 AX1724EZK33 AX6354LTUK AX1724EZK50 AX6601UKP125 AX6821ZUK AX8867ZUK AX8867ZK26 AX8867ZK26 AX8867ZK26 AX8867ZK26	MAX MAX MAX MAX MAX MAX MAX MAX MAX MAX	dede dede dede dede dede mre dede tempsw mre+wdt mre+wdt reg	$ \begin{cases} l_{cc} \le 50 \text{msA} \\ V_{N1} = 0.85.6 \text{B}, V_{OUT} = 25.5 \text{B}, l_{OUT} = 150 \text{mA} \\ V_{N1} = 0.85.5 \text{B}, V_{OUT} = 25.5 \text{B}, l_{OUT} = 150 \text{mA} \\ V_{N1} = 0.85.5 \text{B}, V_{OUT} = 7.0 \text{B}, l_{OUT} = 150 \text{mA} \\ V_{N1} = 0.85.6 \text{B}, V_{OUT} = 3.0 \text{B}, l_{OUT} = 150 \text{mA} \\ V_{N1} = 0.85.6 \text{B}, V_{OUT} = 3.0 \text{B}, l_{OUT} = 150 \text{mA} \\ V_{11} = 4.63 \text{B}, V_{11} = 3.0 \text{B}, V_{10} = 1.25.5 \text{B}, l_{CC} \le 50 \text{msA} \\ V_{CS} = 2.5.5 \text{B}, V_{DUT} = 5.0 \text{B}, l_{OUT} = 150 \text{mA} \\ V_{CD} = 2.75.5 \text{B}, V_{DUT} = 5.5 \text{B}, l_{CC} \le 65 \text{msA} \\ V_{TS} = 2.32 \text{B}, V_{DD} = 125.5 \text{B}, l_{CC} \le 65 \text{msA} \\ V_{TS} = 2.32 \text{B}, V_{DD} = 125.5 \text{B}, l_{CC} \le 30 \text{msA} \\ U_{DC} = 2.752 \text{B}, V_{DUT} = 25.5 \text{B}, l_{CC} \le 30 \text{msA} \\ U_{DC} = 2.752 \text{B}, V_{DUT} = 25.5 \text{B}, l_{CC} \le 50 \text{msA} \\ U_{DC} = 2.752 \text{B}, V_{DUT} = 25.5 \text{B}, l_{CC} \le 50 \text{msA} \\ U_{DC} = 2.752 \text{B}, V_{DUT} = 25.5 \text{B}, l_{CC} \le 50 \text{msA} \\ U_{DC} = 2.752 \text{B}, V_{DUT} = 255 \text{B}, l_{CC} \le 50 \text{msA} \\ U_{DC} = 2.752 \text{B}, V_{DUT} = 255 \text{B}, l_{CC} \le 50 \text{msA} \\ U_{DC} = 2.752 \text{B}, V_{DUT} = 255 \text{B}, l_{CC} \le 50 \text{msA} \\ U_{DC} = 2.752 \text{B}, V_{DUT} = 255 \text{B}, V_{DUT} = 2.55 \text{B}, V_{DUT} = 150 \text{mA} \\ U_{DC} = 2.752 \text{B}, V_{DUT} = 255 \text{B}, V_{DUT} = 2.55 \text{B}, V_$	TSOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 SOT23-5 SOT23-5 SOT23-5 SOT23-5 SOT23-5	BATT + GND + FB + OUT + LX BATT + GND + FB + OUT + LX BATT + GND + FB + OUT + LX BATT + GND + FB + OUT + LX BATT + GND + FB + OUT + LX BATT + GND + FB + OUT + LX BATT + GND + FB + OUT + LX BATT + GND + FB + OUT + LX BATT + GND + FB + OUT + VCC + TOVER RES + GND + FB + OUT + VCC RES + GND + FB + OUT + VCC RES + GND + FB + OUT + VCC RES + GND + FB + OUT + VCC
ADGG MA: ADGJ MA: ADGJ MA: ADGJ MA: ADGJ MA: ADGJ MA: ADGG MA: ADGK MA: ADGM MA: ADG	AX1723EZK AX1724EZK27 AX1724EZK33 AX1724EZK33 AX6354LTUK AX1724EZK50 AX6601UKP125 AX6825YUK AX6825YUK AX8867ZK26 AX8867ZK26 AX8867ZK26 AX8867ZK28	MAX MAX MAX MAX MAX MAX MAX MAX MAX MAX	dede dede dede dede mrc dede tempsw mrc+wdt mrc+wdt reg	$\begin{split} &V_{NI}\!=\!0.85.5B, V_{OUT}\!=\!25.5B, I_{DII}\!=\!150\text{MA} \\ &V_{NI}\!=\!0.85.5B, V_{OUT}\!=\!2.7.7B, I_{OUT}\!=\!150\text{MA} \\ &V_{NI}\!=\!0.85.5B, V_{OUT}\!=\!351, I_{OUT}\!=\!150\text{MA} \\ &V_{NI}\!=\!0.85.5B, V_{OUT}\!=\!3.5B, I_{OUT}\!=\!150\text{MA} \\ &V_{III}\!=\!4.63B, V_{IIR}\!=\!3.08B, V_{OU}\!=\!125.5B, I_{OUT}\!=\!150\text{MA} \\ &V_{III}\!=\!6.85B, V_{OUT}\!=\!50, I_{OUT}\!=\!150\text{MA} \\ &V_{III}\!=\!0.85.5B, V_{OUT}\!=\!5B, I_{OUT}\!=\!150\text{MA} \\ &V_{CC}\!=\!275.5B, T_{TII}\!=\!+125C, I_{CC}\!<\!65\text{MarA} \\ &V_{IIR}\!=\!2.32B, V_{OUT}\!=\!125.5B, I_{CC}\!<\!30\text{MarA} \\ &V_{IIR}\!=\!2.32B, V_{OUT}\!=\!125.5B, I_{CC}\!<\!30\text{MarA} \\ &U_{OUT}\!=\!0.258B, V_{OUT}\!=\!258B, I_{CC}\!<\!30\text{MarA} \\ &U_{OUT}\!=\!0.258B, V_{OUT}\!=\!258B, I_{CC}\!=\!58\text{India} =\!150\text{MA} \end{split}$	TSOT23-5 TSOT23-5 TSOT23-5 TSOT23-5 SOT23-5 TSOT23-5 SOT23-5 SOT23-5 SOT23-5	BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX RST - GND - MR - VCC2 - VCC1 BATT - GND - MR - VCC2 - VCC1 BATT - GND - FB - OUT - LX GND - GND - HYST - VCC - TOVER RES - GND - MR - WDI - VCC RES - GND - RES - WDI - VCC
ADGH MAX ADGU MAX ADG	AX1724EZK27 AX1724EZK30 AX1724EZK33 AX6354LTUK AX1724EZK50 AX6501UKP125 AX6821ZUK AX6825YUK AX8867ZK25 AX8867ZK28 AX8867ZK28	MAX MAX MAX MAX MAX MAX MAX MAX MAX	dodd dodd dodd mrc dodd tempsw mrc+wdt mrc+wdt reg	$\begin{split} & V_{NI}\!=\!0.85.5B, V_{OUT}\!=\!2.7B, I_{OUT}\!=\!150\text{MA} \\ & V_{NI}\!=\!0.85.5B, V_{OUT}\!=\!3.78, I_{OUT}\!=\!150\text{MA} \\ & V_{NI}\!=\!0.85.5B, V_{OUT}\!=\!3.38, I_{OUT}\!=\!150\text{MA} \\ & V_{NI}\!=\!3.38, V_{NI}\!=\!3.08, V_{OU}\!=\!125.5B, I_{OUT}\!=\!150\text{MA} \\ & V_{NI}\!=\!0.85.5B, V_{OUT}\!=\!50, I_{OUT}\!=\!150\text{MA} \\ & V_{NI}\!=\!0.855B, V_{OUT}\!=\!50, I_{OUT}\!=\!150\text{MA} \\ & V_{CC}\!=\!2.75.5B, T_{TH}\!=\!1126\text{CL}, I_{CC}\!<\!26\text{SMcA} \\ & V_{TH}\!=\!2.32B, V_{OUT}\!=\!1.25.5B, I_{CC}\!<\!30\text{MarA} \\ & V_{TH}\!=\!2.19B, V_{DD}\!=\!125.5B, I_{CC}\!<\!30\text{MarA} \\ & U_{DU}\!=\!2.56.5B, V_{OUT}\!=\!2.5B, I_{OUT}\!=\!150\text{MA} \end{split}$	TSOT23-5 TSOT23-5 TSOT23-5 SOT23-5 TSOT23-5 SOT23-5 SOT23-5 SOT23-5	BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX RST - GND - FB - OUT - CX RST - GND - FR - OUT - CX BATT - GND - FR - OUT - CX GND - GND - FR - OUT - CX RES - GND - SNB - WDI - VCC RES - GND - RES - WDI - VCC
ADQI MAX ADQJ MAX ADQJ MAX ADQK MAX ADQL MAX ADQL MAX ADQD MAX ADQW MAX	AX1724EZK30 AX1724EZK33 AX6354LTUK AX1724EZK50 AX6501UKP125 AX6821ZUK AX6825YUK AX8867ZK25 AX8867ZK28 AX8867ZK28	MAX MAX MAX MAX MAX MAX MAX MAX	dcdc dcdc mrc dcdc tempsw mrc+wdt mrc+wdt reg	$\begin{split} & V_{NI}\!=\!0.85.5B, V_{OUT}\!=\!3B, I_{OUT}\!=\!150\text{MA} \\ & V_{NI}\!=\!0.855B, V_{OUT}\!=\!3.05, I_{OUT}\!=\!150\text{MA} \\ & V_{IRS}\!=\!4.63B, V_{IRS}\!=\!3.06B, V_{OUT}\!=\!15.05\text{MA} \\ & V_{IRS}\!=\!4.63B, V_{IRS}\!=\!3.06B, V_{OUT}\!=\!1255B, I_{OUT}\!=\!150\text{MA} \\ & V_{NI}\!=\!2.76.5B, T_{NI}\!=\!142B, C_{ILC}\!<\!85\text{MarA} \\ & V_{IRS}\!=\!2.2B, V_{OUT}\!=\!5B, I_{OUT}\!=\!150\text{MA} \\ & V_{IRS}\!=\!2.2B, V_{OUT}\!=\!1.255B, I_{ICC}\!<\!30\text{MarA} \\ & V_{IRS}\!=\!2.19B, V_{OD}\!=\!1.255B, I_{ICC}\!<\!30\text{MarA} \\ & U_{OUT}\!=\!2.565B, V_{OUT}\!=\!2.5B, I_{OUT}\!=\!150\text{MA} \end{split}$	TSOT23-5 TSOT23-5 SOT23-5 TSOT23-5 SOT23-5 SOT23-5 SOT23-5	BATT - GND - FB - OUT - LX BATT - GND - FB - OUT - LX RST - GND - MR - VCC2 - VCC1 BATT - GND - FB - OUT - LX GND - GND - FB - OUT - LX GND - GND - HYST - VCC - TOVER RES - GND - MR - WDI - VCC RES - GND - RES - WDI - VCC
ADGJ MA: ADGJ MAV ADGK MA: ADGK MA: ADGM MA:	AX1724EZK33 AX6354LTUK AX1724EZK50 AX6501UKP125 AX6821ZUK AX6825YUK AX6825YUK AX6867ZK25 AX6867ZK28 AX6867ZK29	MAX MAX MAX MAX MAX MAX MAX	dodo mrc dodo tempsw mrc+wdt mrc+wdt reg	$\begin{split} & V_{NP} = 0.85.5B, \ V_{OUP} = 3.3 B, \ I_{OUP} = 150 \text{MA} \\ & V_{NP} = 4.63B, \ V_{NP2} = 3.00 B, \ V_{OD} = 1.25.5B, \ I_{CCC} \leq 50 \text{MA} \\ & V_{NP} = 0.85.5B, \ V_{OUP} = 5B, \ I_{OUP} = 150 \text{MA} \\ & V_{CP} = 2.76.5B, \ T_{Th} = 4125 \text{CC}, \ I_{CCC} \leq 85 \text{MeA} \\ & V_{TP} = 2.32 B, V_{OD} = 1.25.5 B, \ I_{CCC} \leq 30 \text{MeA} \\ & V_{TP} = 2.92 B, V_{OD} = 1.25.5 B, \ I_{CCC} \leq 30 \text{MeA} \\ & U_{DCC} = 1.26.5B, \ V_{OUP} = 2.5 B, \ I_{CCC} \leq 30 \text{MeA} \\ & U_{DCC} = 1.255 B, \ V_{OUP} = 1.255 B, \ V_{OUP} = 1.0.0 \text{MA} \end{split}$	TSOT23-5 SOT23-5 TSOT23-5 SOT23-5 SOT23-5 SOT23-5	BATT • GND • FB • OUT • LX RST • GND • MR • VCC2 • VCC1 BATT • GND • FB • OUT • LX GND • GND • HYST • VCC • TOVER RES • GND • MR • WDI • VCC RES • GND • RES • WDI • VCC
ADQJ MAX ADQK MAX ADQK MAX ADQM MAX ADQM MAX ADQP MAX ADQP MAX ADQQ MAX	AX6354LTUK AX1724EZK50 AX6501UKP125 AX6821ZUK AX6825YUK AX8867ZK25 AX8867ZK28 AX8867ZK28	MAX MAX MAX MAX MAX MAX	mrc dodc tempsw mrc+wdt mrc+wdt reg reg	$\begin{split} &V_{IIB} = 4.63B, V_{IIB} = 3.08 B, V_{00} = 1.25.5B; \\ &V_{CC} \le 50 \text{MeA} \\ &V_{CC} = 2.75.5B, V_{OUI} = 5B; I_{OUI} = 150 \text{MA} \\ &V_{CC} = 2.75.5B, T_{TH} = +125 C, I_{CC} \le 65 \text{MeA} \\ &V_{IIB} = 2.32 B, V_{QD} = 125.5B, I_{CC} \le 30 \text{MeA} \\ &V_{IIB} = 2.32 B, V_{QD} = 125.5B, I_{CC} \le 30 \text{MeA} \\ &V_{IIB} = 2.95 B, V_{QUI} = 2.5.8 B, I_{CC} \le 50 \text{MeA} \\ &V_{DC} = 2.75 B, V_{QUI} = 2.5 B, I_{QUI} = 150 \text{MA} \end{split}$	SOT23-5 TSOT23-5 SOT23-5 SOT23-5 SOT23-5	RST • GND • MR • VCC2 • VCC1 BATT • GND • FB • CUT • LX GND • GND • HYST • VCC • TOVER RES • GND • MR • WDI • VCC RES • GND • RES • WDI • VCC
ADOK MAX ADOK MAX ADOK MAX ADOL MAX ADOM MAX ADOM MAX ADOP MAX ADOP MAX ADOP MAX ADOR MAX ADOR MAX ADOR MAX ADOR MAX ADOX MAX	AX1724EZK50 AX6501UKP125 AX6821ZUK AX6825YUK AX6825YUK AX8867ZK25 AX8867ZK28 AX8867ZK28	MAX MAX MAX MAX MAX	dodc tempsw mrc+wdt mrc+wdt reg	$\begin{aligned} & \{c_0: 5.5 \text{ MeA} \\ & V_{NI} = 0.85.5 \text{ B}, V_{DUI} = 5.8; I_{DUI} = 150 \text{ MA} \\ & V_{CC} = 2.75.5 \text{ B}, T_{DII} = 1125 \text{ C}, I_{CC} < 85 \text{ MeA} \\ & V_{TR} = 2.32 \text{ B}, V_{DOI} = 1.25.5 \text{ B}, I_{CC} < 30 \text{ MeA} \\ & V_{TR} = 2.198, V_{DOI} = 1.25.5 \text{ B}, I_{CC} < 30 \text{ MeA} \\ & \{DO, V_{NI} = 2.56.58, V_{DUI} = 2.5.8; I_{DUI} = 150 \text{ MA} \end{aligned}$	TSOT23-5 SOT23-5 SOT23-5 SOT23-5	BATT • GND • FB • CUT • LX GND • GND • HYST • VCC • TOVER RES • GND • MR • WDI • VCC RES • GND • RES • WDI • VCC
ADQK MAXADQA M	AX6501UKP125 AX6821ZUK AX6825YUK AX8867ZK25 AX8867ZK28 AX8867ZK28	MAX MAX MAX MAX	tempsw mrc+wdt mrc+wdt reg reg	$\begin{split} &V_{CC}\!=\!2.75.5B; T_{TH}\!=\!+125\text{°C}; \ I_{CC}\!<\!85\text{MKA} \\ &V_{TB}\!=\!2.32B; V_{DD}\!=\!1.25.5B; \ I_{CC}\!<\!30\text{MKA} \\ &V_{TB}\!=\!2.19B; V_{DD}\!=\!1.25.5B; \ I_{CC}\!<\!30\text{MKA} \\ &L\!DO; V_{IM}\!=\!2.56.5B; V_{DUT}\!=\!2.5B; I_{DUT}\!=\!150\text{MA} \end{split}$	SOT23-5 SOT23-5 SOT23-5	GND • GND • HYST • VCC • TOVER RES • GND • MR • WDI • VCC RES • GND • RES • WDI • VCC
ADQL MAX ADQM MAX ADQM MAX ADQQ MAX ADQW MAX ADQW MAX ADQW MAX	AX6821ZUK AX6825YUK AX8867ZK25 AX8867ZK28 AX8867ZK28	MAX MAX MAX MAX	mrc+wdt mrc+wdt reg reg	$\begin{split} &V_{TB}\!=\!2.32B; V_{DD}\!=\!1.25.5B; I_{CC}\!<\!30\text{mKA} \\ &V_{TB}\!=\!2.19B; V_{DD}\!=\!1.25.5B; I_{CC}\!<\!30\text{mKA} \\ &L\!DO; V_{IN}\!=\!2.56.5B; V_{DUT}\!=\!2.5B; I_{DUT}\!=\!150\text{mA} \end{split}$	SOT23-5 SOT23-5	RES • GND • MR • WDI • VCC RES • GND • RES • WDI • VCC
ADOM MAXADOM M	AX8867ZK25 AX8867ZK25 AX8867ZK28 AX8867ZK29	MAX MAX MAX	mrc+wdt reg reg	V_{TB} =2.19B; V_{DD} =1.25.5B; I_{CC} <30 mKA LDO; V_{IN} =2.56.5B; V_{OUT} =2.5B; I_{OUT} =150 mA	SOT23-5	RES • GND • RES • WDI • VCC
ADOM MAXADOM M	AX8867ZK25 AX8867ZK28 AX8867ZK29	MAX MAX	reg reg	LDO; V _{IN} = 2.56.5B; V _{OUT} = 2.5B; I _{OUT} = 150 mA		
ADQQ MAX ADQP MAX ADQQ MAX ADQQ MAX ADQQ MAX ADQQ MAX ADQQ MAX ADQV MAX ADQW MAX ADQW MAX	AX8867ZK28 AX8867ZK29	MAX	reg	LDO; V _{IN} = 2.56.5B; V _{OUT} = 2.5B; I _{OUT} = 150 mA	TSOT23-5	
ADQP MAX ADQQ MAX ADQQ MAX ADQQ MAX ADQS MAX ADQC MAX ADQV MAX ADQW MAX ADQW MAX	AX8867ZK29					SHDN • GND • IN • CUT • BP
ADQP MAX ADQQ MAX ADQQ MAX ADQR MAX ADQX MAX ADQV MAX ADQW MAX ADQW MAX		MAX			TSOT23-5	SHDN • GND • IN • CUT • BP
ADQQ MAX ADQQ MAX ADQR MAX ADQS MAX ADQT MAX ADQV MAX ADQW MAX	AX9140EUK		reg	LDO; V _{IN} =2.56.5B; V _{OUT} =2.84B; I _{OUT} =150 MA	TSOT23-5	SHDN • GND • IN • CUT • BP
ADQQ MAX ADQR MAX ADQS MAX ADQT MAX ADQV MAX ADQW MAX		MAX	стр	V _{DSI} < 4.5 mB; V _{CC} = 2.75.5 B; I _{CC} < 300 mkA	SOT23-5	OUT • GND • IN+ • IN- • VCC
ADQR MAX ADQS MAX ADQT MAX ADQV MAX ADQW MAX	AX5466EUK	MAX	Dpot	32 позиции; 10 кОм; V _{DD} = 2.75.5 В	SOT23-5	VDD • GND • U/D • CS • H
ADQS MAX ADQT MAX ADQV MAX ADQW MAX	AX8867ZK30	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OLT} =3.0B; I _{OLT} =150 MA	TSOT23-5	SHDN • GND • IN • CUT • BP
ADQV MAX ADQW MAX ADQW MAX	AX8867ZK32	MAX	reg	LDO; V _{IN} =2.56.5B; V _{DLIT} =3.15B; I _{DLIT} =150 MA	TSOT23-5	SHDN • GND • IN • CUT • BP
ADQV MAX ADQW MAX	AX8867ZK33	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =3.3B; I _{OUT} =150 MA	TSOT23-5	SHDN • GND • IN • CUT • BP
ADQW MAX	AX8867ZK36	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =3.6B; I _{OUT} =150 MA	TSOT23-5	SHDN • GND • IN • CUT • BP
ADQW MAX	AX8867ZK50	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =5.0B; I _{OUT} =150mA	TSOT23-5	SHDN • GND • IN • CUT • BP
	AX6352SVUK	MAX	mrc	$V_{TR1} = 2.93 \text{ B}; V_{TR2} = 1.58 \text{ B}; V_{DO} = 1.25.5 \text{ B}; V_{CC} < 50 \text{ MKA}$	SOT23-5	RST • GND • MR • VCC2 • VCC1
ADQX MAX	AX8868ZK25	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =2.5B; I _{OUT} =150mA	TSOT23-5	SHDN • GND • IN • CUT • BP
	AX6353RVUK	MAX	mrc	$V_{TR1} = 2.63 \text{ B}; V_{TR2} = 1.58 \text{ B}; V_{DD} = 1.25.5 \text{ B}; V_{CC} < 50 \text{ mKA}$	SOT23-5	RST • GND • MR • VCC2 • VCC1
ADQX MAX	AX8868ZK28	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =2.8B; I _{OUT} =150 mA	TSOT23-5	SHDN • GND • IN • CUT • BP
ADQY MAX	AX6354SWUK	MAX	mrc	$V_{TR1} = 2.93 \text{ B}; V_{TR2} = 1.67 \text{ B}; V_{DD} = 1.25.5 \text{ B}; V_{CC} \le 50 \text{ mKA}$	SOT23-5	RST • GND • MR • VCC2 • VCC1
ADQY MAX	AX8868ZK29	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =2.84B; I _{OUT} =150 MA	TSOT23-5	SHDN • GND • IN • OUT • BP
ADQZ MAX	AX6354RVUK	MAX	mrc	$V_{TR1} = 2.63 \text{ B}; V_{TR2} = 1.58 \text{ B}; V_{DD} = 1.25.5 \text{ B}; V_{CC} \le 50 \text{ m/s}$	SOT23-5	RST • GND • MR • VCC2 • VCC1
ADQZ MAX	AX8868ZK30	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =3.0B; I _{OUT} =150 mA	TSOT23-5	SHDN • GND • IN • OUT • BP
ADRA MA	AX4350EUK	MAX	OA	R-R; V _{DD} =±4.5±5.5 B; f _{BD} =210MΓu; V _{DSI} <26 mB	SOT23-5	OUT • VEE • IN+ • IN- • VCC
ADRA MA	AX8868ZK32	MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =3.15B; I _{OUT} =150 MA	TSOT23-5	SHDN • GND • IN • OUT • BP
ADRB MA	AX6316MUK46A	MAX	mrc	V _{TR} =4.63 B; V _{DD} =15.5 B; I _{DC} < 20 мкА	SOT23-5	RES • GND • MR • WDI • VCC
ADRB MA		MAX	reg	LDO; V _{IN} =2.56.5B; V _{OUT} =3.3B; I _{OUT} =150 mA	TSOT23-5	SHDN • GND • IN • OUT • BP
ADRC MAX	AX8868ZK33	MAX	mrc	$V_{TR1} = 2.78 \text{ B}; V_{TR2} = 1.58 \text{ B}; V_{DO} = 1.25.5 \text{ B}; V_{CC} \le 50 \text{ mKA}$	SOT23-5	RST • GND • MR • VCC2 • VCC1
ADRC MAX	AX8868ZK33 AX6353UVUK		reg	LDO; V _{IN} =2.56.5B; V _{OUT} =3.6B; I _{OUT} =150 mA	TSOT23-5	SHDN • GND • IN • OUT • BP
ADRD MAX		MAX	OA	R-R; V_{DD} = 2.45.5 B; f_{BD} = 200 kFu; I_{DC} < 60 mkA;	SOT23-5	IN+ • GND • IN- • OUT • VDD



Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1+2+3+4+5
ADRD	MAX8868ZK50	MAX	reg	LDO; V _{IN} = 2.5 6.5 B; V _{OLIT} = 5.0 B; I _{OLIT} = 150 MA	TSOT23-5	SHDN • GND • IN • OUT • BP
ADRE	MAX4466EUK	MAX	OA	R-R; V_{DD} = 2.45.5 B; f_{BD} = 200 kFu; I_{CC} < 60 mkA; V_{DSI} < 5 mB	SOT23-5	IN+ • GND • IN- • OUT • VCC
ADUD	MAX6502UKP125	MAX	tempsw	V _{CC} = 2.7 5.5 B; T _{TH} = +125 °C; I _{CC} < 85 мкА	SOT23-5	GND • GND • HYST • VCC • TOVER
AEA	AD8631ART	AD	OA	f ₈₀ = 5 МГц; P _D = 3 мВт; V _{DD} = 1.86 В	SOT23-5	OUT A • V - • +IN A • -IN A • V+
ALW	TPS62208DBV	TI	dodo	V _{IN} = 2.56.0B; V _{OUT} = 1.875B; I _{OUT} = 300 mA	SOT23-5	VI • GND • EN • FB • SW
HOA	AD8515AKSZ	AD	OA	$f_{BD} = 5 M \Gamma_{IJ}; P_D = 3 MBT; V_{DD} = 1.85B$	SOT353, SC88A	OUT • V - • + IN • - IN • V+
HOA	AD8515ARTZ	AD	OA	f ₈₀ = 5 МГц; P ₀ = 3 мВт; V ₀₀ = 1.85 В	SOT23-5	OUT • V - • + IN • - IN • V+
AQ	AN 1433SSM	PAN	reg	V _{IN} = 1.2514 B; I _{CAT} < 20 mA; V _{DUT} = 1.2515 B	SOT553, EMT5	VCC ◆ ANODE ◆ CATHODE ◆ n. c. ◆ REF
ASA	AD8565AKS	AD	OA	$f_{BD} = 5 M\Gamma u; P_D = 12 MBT; V_{DD} = 4.516 B$	SOT353, SC88A	OUT • V+ • +IN • -IN • V-
B3A	AD8605ART	AD	OA	$f_{8D} = 10 \text{ MFu}; P_D = 7 \text{ MBT}; V_{DD} = 2.75.5 \text{ B}$	SOT23-5	OUT • V - • + IN • -IN • V+
B3A#	AD8605ARTZ	AD	OA	$f_{BD} = 10 M\Gamma u; P_D = 7 MBT; V_{DD} = 2.75.5 B$	SOT23-5	OUT • V - • + IN • - IN • V+
B43	OPA343NA	TI	OA	R-R; V _{DD} = 2.55.5 B; f _{BD} = 5.5 MFu; I _S = 1.4 mA; V _{DSI} < ±8 mB	SOT23-5	OUT • V - • + IN • - IN • V+
B9A	AD8627AKS	AD	OA	$f_{BD} = 5 M\Gamma u; P_D = 25 MBT; V_{DD} = 526/\pm 2.5\pm 13 B$	SOT353, SC88A	OUT A • V - • +IN • -IN • V+
BA	AN80L18RMS	PAN	reg	LDO; V _{IN} = 2.8 B; I _{DLIT} = 150 mA; V _{DLIT} = 1.8 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BB	AN80L19RMS	PAN	reg	LDO; V _{IN} = 2.9 B; I _{DUT} = 150 mA; V _{DUT} = 1.9 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BC	AN80L20RMS	PAN	reg	LDO; V _{IN} = 3.0 B; I _{OUT} = 150 mA; V _{OUT} = 2.0 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BD	AN80L21RMS	PAN	reg	LDO; V _{IN} = 3.1 B; I _{DUI} = 150 mA; V _{DUI} = 2.1 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BDA	AD8515AKS	AD	OA	$f_{BD} = 5 M \Gamma_{II}; P_D = 3 MB T; V_{DD} = 1.85 B$	SOT353, SC88A	OUT • V - • + IN • - IN • V+
BDA	AD8515ART	AD	OA	f ₈₀ = 5 МГц; P ₀ = 3 мВт; V ₀₀ = 1.85 В	SOT23-5	OUT • V - • + IN • - IN • V+
BE	AN80L22RMS	PAN	reg	LDO; V _{IN} = 3.2 B; I _{OUT} = 150 mA; V _{OUT} = 2.2 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BF	AN80L28RMS	PAN	reg	LDO; V _{IN} = 3.8 B; I _{DUT} = 150 mA; V _{DUT} = 2.8 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BG	AN80L29RMS	PAN	reg	LDO; V _{IN} = 3.9 B; I _{OUT} = 150 mA; V _{OUT} = 2.9 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BH	AN80L30RMS	PAN	reg	LDO; V _{IN} = 4.0 B; I _{OUT} = 150 mA; V _{OUT} = 3.0 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BJ	AN80L31RMS	PAN	reg	LDO; V _{IN} = 4.1 B; I _{DUT} = 150 mA; V _{DUT} = 3.1 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BK	AN80L32RMS	PAN	reg	LDO; V _{IN} = 4.2 B; I _{DUI} = 150 mA; V _{DUI} = 3.2 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BL	AN80L33RMS	PAN	reg	LDO; V _{IN} = 4.3 B; I _{DUI} = 150 mA; V _{DUI} = 3.3 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BM	AN80L34RMS	PAN	reg	LDO; V _{IN} = 4.4 B; I _{OUT} = 150 mA; V _{OUT} = 3.4 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BN	AN80L35RMS	PAN	reg	LDO; V _{IN} = 4.5 B; I _{OUT} = 150 mA; V _{OUT} = 3.5 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BP	AN80L36RMS	PAN	reg	LDO; V _{IN} = 4.6 B; I _{OUT} = 150 mA; V _{OUT} = 3.6 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BQ	AN80L48RMS	PAN	reg	LDO; V _{IN} = 5.8 B; I _{DUI} = 150 mA; V _{DUI} = 4.8 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BR	AN80L49RMS	PAN	reg	LDO; V _{IN} = 5.9 B; I _{DUI} = 150 mA; V _{DUI} = 4.9 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BS	AN80L50RMS	PAN	reg	LDO; V _{IN} = 6.0 B; I _{DUI} = 150 mA; V _{DUI} = 5.0 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BT	AN80L51RMS	PAN	reg	LDO; V _{IN} = 6.1 B; I _{DUT} = 150 mA; V _{DUT} = 5.1 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BU	AN80L52RMS	PAN	reg	LDO; V _{IN} = 6.2 B; I _{DUT} = 150 mA; V _{DUT} = 5.2 B	SOT23-5	CONT • GND • n. c. • OUT • IN
BW	AN80L25RMS	PAN	reg	LDO; V _{IN} = 3.5 B; I _{OUT} = 150 mA; V _{OUT} = 2.5 B	SOT23-5	CONT • GND • n. c. • OUT • IN
C1	FMC1A	ROHM	Dpnp/npn	V _{CC} =50B; I _{OUT} =100 mA; P _D =300 mBT; h ₂₁ >56	SOT23-5	C1 • C2 • E2, B2 • B1 • E1
C1	UMC1N	ROHM	Dpnp/npn	V_{CC} = 50B; I_{OUT} = 100 mA; P_D = 150 mB; h_{21} > 56	SOT353, SC88A	E1 • B1 • E2, B2 • C2 • C1
C12	LMV331M5	NS	стр	V _{DSI} < 7mB; V _{DD} = 2.75 B; I _{CC} < 100 mkA	SOT23-5	+IN • V- • -IN • OUT • V+
C13	LMV331M7	NS	стр	$V_{OSI} < 7 \text{mB}; V_{OO} = 2.75 \text{ B}; I_{CC} < 100 \text{ mkA}$	SOT353, SC88A	+IN • V- • -IN • OUT • V+
C2	EMC2	ROHM	Dpnp/npn	V_{CC} =50B; I_{OUT} =100 mA; P_D =150 mBt; h_{21} >56; 22 kOm/22 kOm	SOT553, EMT5	E1 • B1 • E2, B2 • C2 • C1
C2	FMC2A	ROHM	Dpnp/npn	V_{CC} = 50 B; I_{OUT} = 100 mA; P_D = 300 mB1; h_{21} > 56; 22 kOm/22 kOm	SOT23-5	C1 • C2 • E2, B2 • B1 • E1
C2	UMC2N	ROHM	Dpnp/npn	V _{CC} =50B; I _{OUT} =100 мА; P _D =150 мВт; h ₂₁ >56; 22 кОм/22 кОм	SOT353, SC88A	E1 • B1 • E2, B2 • C2 • C1





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5
C3	FMC3A	ROHM	Dpnp/npn	V _{CC} = 50B; I _{OUT} = 100 mA; P _D = 300 mBT; h ₂₁ > 56; 10 kOm/10 kOm	SOT23-5	C1 • C2 • E2, B2 • B1 • E1
C3	UMC3N	ROHM	Dpnp/npn	$V_{CC} = 50B$; $I_{DUT} = 100 \text{ mA}$; $P_D = 150 \text{ mBT}$; $h_{21} > 56$; $10 \text{ KOM}/10 \text{ KOM}$	SOT353, SC88A	E1 • B1 • E2, B2 • C2 • C1
C4	FMC4A	ROHM	Dpnp/npn	V _{CC} =50B; I _{OUT} =100 мА; P _D =300 мВт; h ₂₁ >56; 47 кОм/47 кОм; 47 кОм/10 кОм	SOT23-5	C1 • C2 • E2, B2 • B1 • E1
C4	UMC4N	ROHM	Dpnp/npn	V _{CC} = 50B; I _{OUT} = 100 mA; P _D = 150 mBT; h ₂₁ > 56; 47 kOm/47 kOm; 47 kOm/10 kOm	SOT353, SC88A	E1 • B1 • E2, B2 • C2 • C1
C5	FMC5A	ROHM	Dpnp/npn	V _{CC} = 50B; I _{OUT} = 100 mA; P _D = 300 mBT; h ₂₁ > 56; 47 kOm/47 kOm; 4.7 kOm/10 kOm	SOT23-5	C1 • C2 • E2, B2 • B1 • E1
C5	UMC5N	ROHM	Dpnp/npn	V_{CC} = 50B; I_{OUT} = 100 mA; P_D = 150 mBT; h_{21} > 56; 47 kOm/47 kOm; 4.7 kOm/10 kOm	SOT353, SC88A	E1 • B1 • E2, B2 • C2 • C1
C6	FMC6A	ROHM	Dpnp/npn	V_{CC} = 50B; I_{OUT} = 100 mA; P_D = 300 mBT; h_{21} > 56; 100 kOm/100 kOm	SOT23-5	C1 • C2 • E2, B2 • B1 • E1
C6	UMC6N	ROHM	Dpnp/npn	V _{CC} = 50B; I _{OUT} = 100 mA; P _D = 150 mBT; h ₂₁ > 56; 100 kOm/100 kOm	SOT353, SC88A	E1 • B1 • E2, B2 • C2 • C1
C7	FMC7A	ROHM	Dpnp/npn	V _{CC} = 50B; I _{OUT} = 100 MA; P _D = 300 MBT; h ₂₁ > 56	SOT23-5	C1 • C2 • E2, B2 • B1 • E1
C7	UMC7N	ROHM	Dpnp/npn	V _{CC} = 50B; I _{OUT} = 100 mA; P _D = 150 mBT; h ₂₁ > 56	SOT353, SC88A	E1 • B1 • E2, B2 • C2 • C1
CGA	AD7415ART	AD	dts	10-разр.; SMBus/I ² C; V _{DD} =2.75.5В	SOT23-5	AS • GND • VDD • SDA • SCL
CGB	AD7415ART	AD	dts	10-pasp ; SMBus/I ² C; V ₀₀ =2.75.5B	SOT23-5	AS • GND • VDD • SDA • SCL
D43	OPA743NA	TI	OA	R-R; V_{00} =3.512/±1.75±6 B; f_{80} =7 MFu; I_S =1.7 mA; V_{0SI} <±7 mB	SOT23-5	OUT • V - • + IN • - IN • V+
D53	OPA353NA	TI	OA	R-R; V_{DD} = 2.75.5 B; f_{BD} = 44 MFu; I_S = 9 mA; V_{DSI} < ±10 mB	SOT23-5	OUT • V - • + IN • - IN • V+
DNC	ADP3309ART-2.7	AD	reg	LDO; V _{IN} =2.812B; I _{OUT} =100 mA; V _{OUT} =2.7B	SOT23-5	IN • GND • SD • ERR/n. c. • OUT
DPC	ADP3309ART-3	AD	reg	LDO; V _{IN} = 2.812 B; I _{OUT} = 100 mA; V _{OUT} = 3 B	SOT23-5	IN • GND • SD • ERR/n. c. • OUT
DRC	ADP3309ART-3.3	AD	reg	LDO; V _{IN} = 2.812 B; I _{OUT} = 100 mA; V _{OUT} = 3.3B	SOT23-5	IN • GND • SD • ERR/n. c. • OUT
DTC	ADP3309ART-3.6	AD	reg	LDO; V _{IN} = 2.812 B; I _{OUT} = 100 mA; V _{OUT} = 3.6B	SOT23-5	IN • GND • SD • ERR/n. c. • OUT
DVC	ADP3309ART-2.85	AD	reg	LDO; V _{IN} =2.812B; I _{OUT} =100 mA; V _{OUT} =2.85B	SOT23-5	IN • GND • SD • ERR/n. c. • OUT
DWC	ADP3309ART-2.9	AD	reg	LDO; V _{IN} =2.812B; I _{OUT} =100mA; V _{OUT} =2.9B	SOT23-5	IN • GND • SD • ERR/n. c. • OUT
E37	OPA137NA	TI	OA	$V_{DD} = 4.536/\pm 2.25\pm 18 \text{ B; I}_S = 320 \text{ m/sA;}$ $V_{DS} < \pm 7 \text{ mB}$	SOT23-5	OUT • V - • + IN • - IN • V+
EV	1SV241	SANY O	pin x2	$V_B > 50 B$; $I_F < 50 mA$; $V_F (I_F = 50 mA) = 0.95 B$; $I_B < 0.1 mKA$	SOT23-5	A1 • n. c. • A2 • K2 • K1
G1	EMG1	ROHM	Dnpn x2	V_{CC} = 50B; I_{DUT} = 100 mA; P_D = 150 mBT; h_{21} > 56; 22 kOm/22 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
G1	FMG1A	ROHM	Dnpn x2	V_{CC} = 50B; I_{OUT} = 100 mA; P_{O} = 300 mBT; h_{21} > 56; 22 kOm/22 kOm	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
G1	UMG1N	ROHM	Dnpn x2	$V_{CC} = 50B$; $I_{DUT} = 100 \text{ mA}$; $P_D = 150 \text{ mBT}$; $h_{21} > 56$; $22 \text{ kOm}/22 \text{ kOm}$	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
G10	UMG10N	ROHM	Dnpn x2	$V_{CC} = 50B$; $I_{OUT} = 100$ mA; $P_D = 150$ mBT; $h_{21} > 33$; $R2/R1 = 10$	SOT353, SC88A	C1 • C2 • B2 • E1, E2 • B1
G11	EMG11	ROHM	Dnpn x2	V_{CC} = 50B; I_{OUT} = 100 mA; P_D = 150 mBT; h_{21} > 56; R2/R1 = 21	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
G11	FMG11A	ROHM	Dnpn x2	V_{CC} =50B; I_{OUT} =100 mA; P_D =300 mBT; h_{21} >56; R2/R1=21	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
G11	UMG11N	ROHM	Dnpn x2	V_{CC} = 50B; I_{OUT} = 100 mA; P_D = 150 mBT; h_{21} > 56; $R2/R1$ = 21	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
G2	FMG2A	ROHM	Dnpn x2	$V_{CC} = 50B$; $I_{OUT} = 100$ mA; $P_D = 300$ mBT; $h_{21} > 56$; 47 kOm/ 47 kOm	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
G2	UMG2N	ROHM	Dnpn x2	V_{CC} = 50B; I_{OUT} = 100 mA; P_D = 150 mBT; h_{21} > 56; 47 kOm/47 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
G3	IMG3A	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 300 mBT; h_{21} > 100; R14.7 kOm	SOT23-5	B2 • B1 • C2 • E1,E1 • C1
G37	OPA337NA	TI	OA	R-R; V_{DD} = 2.55.5 B; f_{BD} = 3MFu; I_S = 1.2 mA; V_{DSI} < ±3.5 mB	SOT23-5	OUT • V - • + IN • - IN • V+



SOT553 1 5 4 SOT353 SOT23-5 1 5 5 SC88A TSOT23-5 2 1 6 5

Код	Типономинал	Б	Ф	Особенности	Корпус	L: 1•2•3•4•5
34	EMG4					
		507.5755	Dnpn x2	V_{CBO} =50B; I_C =100mA; P_D =150mBT; h_{21} >100; R1 10 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
G4	FMG4A	ROHM	Dnpn x2	V_{CBD} =50B; I_C =100mA; P_D =300 mBT; h_{21} >100; R1 10 kOm	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
34	UMG4N	ROHM	Dnpn x2	V_{CBD} =50B; I_C =100 mA; P_D =150 mBT; h_{21} >100; R1 10 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
G5	EMG5	ROHM	Dnpn x2	V_{CBO} = 50 B; I_C = 100 mA; P_D = 150 mBr; h_{21} > 100; 10 kOm/47 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
G5	FMG5A	ROHM	Dnpn x2	V_{CBO} =50B; I_C =100 mA; P_D =300 mB1; h_{21} >100; 10 kOm/47 kOm	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
G5	UMG5N	ROHM	Dnpn x2	V _{CBO} =50B; I _C =100mA; P _D =150 mBt; h ₂₁ >100; 10 kOm/47 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
G5	UMG5N	ROHM	Dnpn x2	V_{CC} =50B; I_{DUT} =100 mA; P_D =150 mBT; h_{21} >68; R2/R1=4.7	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
G6	EMG6	ROHM	Dnpn x2	V_{CBD} =50B; I_C =100 mA; P_D =150 mBr; h_{21} >100; R1 47 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
G6	FMG6A	ROHM	Dnpn x2	V_{CBO} =50B; I_C =100 mA; P_D =300 mBr; h_{21} >100; R147 kOm	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
G6	UMG6N	ROHM	Dnpn x2	V_{CBO} =50B; I_C =100mA; P_D =150 mBt; h_{21} >100; R147 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
G6	UMG6N	ROHM	Dnpn x2	$V_{CB} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 150 \text{ mBT}; h_{21} > 100; R_1 = 47 \text{ kOm}$	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
G7	FMG7A	ROHM	Dnpn x2	V_{CBD} =50B; I_C =100mA; P_D =300 mBr; h_{21} >100	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
G7	UMG7N	ROHM	Dnpn x2	V_{CBO} = 50B; I_C = 100 mA; P_D = 150 mBr; h_{21} > 100	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
G7	UMG7N	ROHM	Dnpn x2	V_{CB} = 50 B; I_C = 100 mA; P_D = 150 mBT; h_{21} > 100; R_1 = 10 kOm	SOT353, SC88A	B1 • E1 • E2 • C2 • C1, B2
G8	EMG8	ROHM	Dnpn x2	V_{CBD} =50B; I_C =100mA; P_D =150 mBt; h_{21} >100; 4.7 kOm/47 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
G8	FMG8A	ROHM	Dnpn x2	V_{CBO} =50B; I_C =100 mA; P_D =300 mBT; h_{21} >100; 4.7 kOm/47 kOm	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
G8	UMG8N	ROHM	Dnpn x2	V_{CBO} =50B; I_C =100 mA; P_D =150 mBT; h_{21} >100; 4.7 kOm/47 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
G8	UMG8N	ROHM	Dnpn x2	V_{CC} =50B; I_{OUT} =100 mA; P_D =150 mBT; h_{21} >80; R2/R1=10	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
G9	EMG9	200000000000000000000000000000000000000	Dnpn x2	V_{CC} =50B; I_{OUT} =100 mA; P_D =150 mBT; h_{21} >56; 10 кОм/10 кОм	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
G9	FMG9A	123053340	Dnpn x2	V_{CC} =50B; I_{OUT} =100 mA; P_D =300 mBt; h_{21} >56; 10 kOm/10 kOm	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
G9	UMG9N		Dnpn x2	V_{CC} =50B; I_{OUT} =100 mA; P_D =150 mBT; h_{21} >56; 10 kOm/10 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
HOA	AD8031ART	AD	OA	$f_{BD} = 80 \text{ MFu}; P_D = 16 \text{ MBT}; V_{DD} = 2.712 \text{ B}$	SOT23-5	VOUT • -VS • +IN • -IN • +VS
HOD	AD8061ARTZ	AD	OA	f _{BD} = 320 МГц; P _D = 75 мВт; V _{DD} = 2.78 В	SOT23-5	VOUT • -VS • +IN • -IN • +VS
H1A	AD8005AR	AD	OA	$f_{BD} = 270 \text{ MFu}; P_D = 4 \text{ MBT}; V_{DD} = \pm 3 \pm 6 \text{ B}$	SOT23-5	OUT • -VS • +IN • -IN • +VS
H2A	AD8051ART	AD	OA	$f_{BD} = 110 \text{ MFu}; P_D = 60 \text{ MBT}; V_{DD} = 312 \text{ B}$	SOT23-5	VOUT • -VS • +IN • -IN • +VS
НЗА	AD8055ART	AD	OA	$f_{BD} = 300 \text{ MFu}; P_D = 40 \text{ MBT}; V_{DD} = \pm 4 \pm 6 \text{ B}$	SOT23-5	VOUT • -VS • +IN • -IN • +VS
H3B	AD8033AKS	AD	OA	f _{BD} = 80 МГц; P _D = 65 мВт; V _{DD} = 524 В	SOT353, SC88A	VOUT • -VS • +IN • -IN • +VS
H4	EMH4		Dnpn x2	V_{CBD} =50B; I_C =100mA; P_D =150 mBT; h_{21} >100; R1 10 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
H7A	AD8057ART	AD	OA	$f_{BD} = 325 M\Gamma ц; P_D = 70 MB т; V_{DD} = 312 B$	SOT23-5	VOUT • -VS • +IN • -IN • +VS
HAA	AD8014ART	AD	OA	$f_{BD} = 480 \text{ MFu}; P_D = 8 \text{ MBT}; V_{DD} = \pm 2.25\pm 6 \text{ B}$	SOT23-5	VOUT • -VS • +IN • -IN • +VS
HEA	AD8001ART	AD	OA	f_{BO} < 880 MFL; P_D = 50 MBT; V_{DO} = ±3±6 B	SOT23-5	VOUT • -VS • +IN • -IN • +VS
HGA	AD8061ART	AD	OA	f _{BD} = 320 МГц; P _D = 75 мВт; V _{DD} = 2.78 В	SOT23-5	VOUT • -VS • +IN • -IN • +VS
HRA	AD8065ART	AD	OA	$f_{BD} = 145 \text{ MFu}; P_D = 150 \text{ MBT}; V_{DO} = 524 \text{ B}$	SOT23-5	VOUT • -VS • +IN • -IN • +VS
HRA#	AD8065ARTZ	AD	OA	$f_{BD} = 145 \text{ MFu}; P_D = 150 \text{ MBT}; V_{DD} = 524 \text{ B}$	SOT23-5	VOUT • -VS • +IN • -IN • +VS
HTA	AD8007AKS	AD	OA	$f_{BD} = 650 \text{ MFu}; P_D = 120 \text{ MBT}; V_{DO} = 512 \text{ B}$	SOT353, SC88A	VOUT • -VS • +IN • -IN • +VS





Код	Типономинал	Б	ф	Особенности	Корпус	Ц: 1•2•3•4•5
HUA	AD8038AKS	AD	OA	f ₈₀ =350 МГц; P ₀ =18 мВт; V ₀₀ =312 В	SOT353, SC88A	VOUT •-VS•+IN•-IN•+VS
HVA	AD8091ART	AD	OA	f _{BD} =110 МГц; P _D =60 мВт; V _{DD} =312 В	SOT23-5	VOUT • - VS • + IN • - IN • + VS
HVA#	AD8091ARTZ	AD	OA	f _{BD} =110 МГц; P _D =60 мВт; V _{DD} =312 В	SOT23-5	VOUT • -VS • +IN • -IN • +VS
J36	OPA336NJ	TI	OA	R-R; V _{DD} =2.35.5 B; I _S =42 mKA; V _{DS} <±125 mKB	SOT23-5	OUT • V - • + IN • - IN • V+
K 1	UM5K1N	ROHM	nMOS x2	$V_{DS} = 30 \text{ B; } I_D = 100 \text{ mA; } P_D = 150 \text{ mBT; } P_{DS(on)} < 130 \text{ m}$	SOT353, SC88A	G1 • S1, S2 • G2 • D2 • D1
L1	UML1N	ROHM	pnp+di	V_{CBD} = 60 B; I_C = 150 mA; h_{21} > 120; V_R = 80 B; I_C = 100 mA; $V_C (I_C$ = 100 mA) < 1.2 B	SOT353, SC88A	A•E•B•C•K
L2	UML2N	ROHM	npn+di	V_{CBD} = 60 B; I_C = 150 mA; h_{21} > 120; V_R = 80 B; I_F = 100 mA; V_F (I_F = 100 mA) < 1.2 B	SOT353, SC88A	A•E•B•C•K
LA	MC74LCX1G14	ON	Schminv	V _{CC} = 2.03.6B; I _{OUT} = 24 mA	SOT23-5	n. c. • INA • GND • OUT Y • VCC
LAG	MC78LC15NTR	ON	reg	LDO; V _{IN} = 2.5 12B; V _{OUT} = 1.5B; I _{OUT} = 50 mA	SOT23-5	GND • VIN • VOUT • n. c. • n. c.
LAH	MC78LC18NTR	ON	reg	LDO; V _{IN} =2.512B; V _{OUT} =1.8B; I _{OUT} =50 mA	SOT23-5	GND • VIN • VOUT • n. c. • n. c.
LAI	MC78LC25NTR	ON	reg	LDO; V _{IN} =2.512B; V _{OUT} =2.5B; I _{OUT} =50 MA	SOT23-5	GND • VIN • VOUT • n. c. • n. c.
LAJ	MC78LC27NTR	ON	reg	LDO; V _{IN} =2.512B; V _{OUT} =2.7B; I _{OUT} =50 MA	SOT23-5	GND • VIN • VOUT • n. c. • n. c.
LAK	MC78LC28NTR	ON	reg	LDO; V _{IN} = 2.5 12B; V _{OUT} = 2.8 B; I _{OUT} = 50 mA	SOT23-5	GND • VIN • VOUT • n. c. • n. c.
LAL	MC78LC30NTR	ON	reg	LDO; V _{IN} =2.512B; V _{OUT} =3.0B; I _{OUT} =50 mA	SOT23-5	GND • VIN • VOUT • n. c. • n. c.
LAM	MC78LC33NTR	ON	reg	LDO; V _{IN} =2.512B; V _{OUT} =3.3B; I _{OUT} =50 mA	SOT23-5	GND • VIN • VOUT • n. c. • n. c.
LAN	MC78LC50NTR	ON	reg	LDO; V _{IN} =2.512B; V _{OUT} =5.0B; I _{OUT} =50mA	SOT23-5	GND ◆VIN ◆VOUT ◆ n. c. ◆ n. c.
LDE	ADP3309ART-2.5	AD	reg	LDO; V _{IN} = 2.8 12 B; I _{OUT} = 100 mA; V _{OUT} = 2.5 B	SOT23-5	IN • GND • SD • ERR/n. c. • OUT
LEC	MC78LC40NTR	ON	reg	LDO; V _{IN} =2.512B; V _{OUT} =4.0B; I _{OUT} =50 mA	SOT23-5	GND ◆VIN ◆VOUT ◆n. c. ◆n. c.
LV	1SV265	SANY	pin x2	V _B > 50B; I _E < 50 mA; V _E (I _E = 50 mA) = 0.91 B; I _B < 0.1 mkA	SOT23-5	A1 • n. c. • A2 • K2 • K1
OAQI	OPA842IDBV	TI	OA	$V_{DD} = \pm 5 \pm 6 \text{ B}; f_{BD} = 200 \text{ MFu}; I_S = 22.5 \text{ mA}; V_{DS} < \pm 1.5 \text{ mB}$	SOT23-5	OUT • V - • + IN • - IN • V+
PAPI	TPS3823-25DBV	TI.	mrc+wdt	V _{TR} =2.25 B; V _{DD} =1.15.5 B; I _{CC} <25 mKA	SOT23-5	RES • GND • MR • WDI • VDD
PAQI	TPS3823-30DBV	TI	mrc+wdt	V _{TR} =2.63 B; V _{DD} =1.15.5 B; I _{CC} <25 mkA	SOT23-5	RES • GND • MR • WDI • VDD
PARI	TPS3823-33DBV	TI	mrc+wdt	V _{TR} =2.93 B; V _{DD} =1.15.5 B; I _{CC} < 25 мкА	SOT23-5	RES • GND • MR • WDI • VDD
PASI	TPS3823-50DBV	TI	mrc+wdt	V _{TR} =4.55 B; V _{DD} =1.15.5 B; I _{CC} < 25 mKA	SOT23-5	RES • GND • MR • WDI • VDD
PATI	TPS3824-25DBV	TI	mrc+wdt	V _{TB} =2.25 B; V _{DD} =1.15.5 B; I _{CC} < 25 мкА	SOT23-5	RES • GND • RES • WDI • VDD
PAUI	TPS3824-30DBV	TI	mrc+wdt	V _{TB} =2.63 B; V _{DD} =1.15.5 B; I _{CC} <25 mkA	SOT23-5	RES • GND • RES • WDI • VDD
PAVI	TPS3824-33DBV	TI	mrc+wdt	V _{TB} =2.93 B; V _{DD} =1.15.5 B; I _{CC} <25 мкА	SOT23-5	RES • GND • RES • WDI • VDD
PAWI	TPS3824-50DBV	TI	mrc+wdt	V _{TB} =4.55 B; V _{DD} = 1.15.5 B; I _{CC} < 25 MKA	SOT23-5	RES • GND • RES • WDI • VDD
PCPI	TPS77001DBV	П	reg	LDO; V _{IN} =2.710.0 B; V _{OUT} =1.25.5 B; I _{OUT} =50 MA	SOT23-5	IN • GND • EN • NC/FB • OUT
PCQI	TPS77012DBV	TI	reg	LDO; V _{IN} = 2.7 10.0 B; V _{OUT} = 1.2 B; I _{OUT} = 50 mA	SOT23-5	IN • GND • EN • NC/FB • OUT
PCQI	TPS77018DBV	TI	reg	LDO; V _{IN} = 2.7 10.0 B; V _{OUT} = 1.8 B; I _{OUT} = 50 mA	SOT23-5	IN • GND • EN • NC/FB • OUT
PCRI	TPS77015DBV	TI	reg	LDO; V _{IN} = 2.7 10.0 B; V _{OUT} = 1.5 B; I _{OUT} = 50 mA	SOT23-5	IN • GND • EN • NC/FB • OUT
PCTI	TPS77025DBV	TI	reg	LDO; V _{IN} = 2.7 10.0 B; V _{OUT} = 2.5 B; I _{OUT} = 50 mA	SOT23-5	IN • GND • EN • NC/FB • OUT
PCUI	TPS77027DBV	TI	reg	LDO; V _{IN} =2.710.0 B; V _{OUT} =2.7B; I _{OUT} =50 MA	SOT23-5	IN • GND • EN • NC/FB • OUT
PCVI	TPS77028DBV	TI	reg	LDO; V _{IN} =2.710.0 B; V _{OUT} =2.8 B; I _{OUT} =50 MA	SOT23-5	IN • GND • EN • NC/FB • OUT
PCWI	TPS77030DBV	TI	rea	LDO; V _{IN} =2.710.0 B; V _{OUT} =3.0 B; I _{OUT} =50 MA	SOT23-5	IN • GND • EN • NC/FB • OUT
PCXI	TPS77033DBV	ī	reg	LDC; V _{IN} =2.710.0 B; V _{OIT} =3.3B; I _{OIT} =50 MA	SOT23-5	IN • GND • EN • NC/FB • CUT
PCYI	TPS77050DBV	TI	reg	LDC; V _{IN} = 2.710.0 B; V _{OLT} = 5.0 B; I _{OLT} = 50 MA	SOT23-5	IN • GND • EN • NC/FB • OUT
PDDI	TPS3820-50DBV	TI	mrc+wdt	V _{TB} =4.55 B; V _{DD} =1.15.5 B; I _{CC} <25 мкА	SOT23-5	RES • GND • MR • WDI • VDD
PDE	TPS3820-33DBV	Ti	mrc+wdt	V _{TB} =2.93 B; V _{DD} =1.15.5 B; I _{CC} <25 мкА	SOT23-5	RES • GND • MR • WDI • VDD
PDFI	TPS3825-50DBV	TI	mrc+wdt	V _{TR} = 4.55 B; V _{DD} = 1.15.5 B; I _{CC} < 25 мкА	SOT23-5	RES • GND • RES • MR • VDD
PDGI	TPS3825-33DBV	TI	mrc+wdt	V _{TB} =2.93 B; V _{DD} =1.15.5 B; I _{CC} <25 MKA	SOT23-5	RES • GND • RES • MR • VDD
PDHI	TPS3828-50DBV	TI	mrc+wdt	V _{TR} =4.55 B; V _{DD} =1.15.5 B; I _{CC} <25 мкА	SOT23-5	RES • GND • MR • WDI • VDD
PDII	TPS3828-33DBV	TI	mrc+wdt	V _{TR} =2.93 B; V _{DD} =1.15.5 B; I _{CC} <25 MKA	SOT23-5	RES • GND • MR • WDI • VDD
PHKI	TPS62200DBV	TI	dede		SOT23-5	VI • GND • BN • FB • SW
		TI		V _{IN} = 2.56.0 B; V _{OUT} = 0.7V _{IN} B; I _{OUT} = 300 mA		
PHLI	TPS62201DBV	ĮII.	dede	V _{IN} = 2.56.0 B; V _{OUT} = 1.5 B; I _{OUT} = 300 mA	SOT23-5	VI • GND • EN • FB • SW







Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5
PHMI TI	PS62202DBV	TI	dodc	V _{IN} = 2.56.0B; V _{OUT} = 1.8B; I _{OUT} = 300 mA	SOT23-5	VI • GND • EN • FB • SW
PHNI TI	PS62203DBV	TI	dodo	V _{IN} = 2.56.0B; V _{OUT} = 3.3B; I _{OUT} = 300 mA	SOT23-5	VI • GND • EN • FB • SW
PHSI TI	PS62204DBV	TI	dodo	V _{IN} = 2.56.0B; V _{OUT} = 1.6B; I _{OUT} = 300 mA	SOT23-5	VI • GND • EN • FB • SW
PHTI TI	PS62205DBV	TI	dcdc	V _{IN} = 2.56.0B; V _{OLIT} = 2.5B; I _{OLIT} = 300 mA	SOT23-5	VI • GND • EN • FB • SW
PJGI TI	PS62207DBV	TI	dodo	V _{IN} = 2.56.0B; V _{OUT} = 1.2B; I _{OUT} = 300 mA	SOT23-5	VI • GND • EN • FB • SW
Q2 FI	MQ2	ROHM	Dnpn x2	V_{CBO} =40B; I_C =30mA; P_D =300mBT; h_{21} >120; 100 kOm/100 kOm/200 Om	SOT23-5	E2 • B2, E2 • C1 • B1 • C2
RO2A LI	M4130AIM5-2.0	NS	vref	V _{OUT} = 2.0 B; ACC = 0.05 %; 10 ppm/°C	SOT23-5	n. c. • GND • n. c. • VIN • VREF
R02B LI	M4130BIM5-2.0	NS	vref	V _{OUT} = 2.0 B; ACC = 0.2 %; 10 ppm/°C	SOT23-5	n. c. • GND • n. c. • VIN • VREF
RO2C LI	M4130CIM5-2.0	NS	vref	V _{OUT} = 2.0 B; ACC = 0.1 %; 20 ppm/°C	SOT23-5	n. c. • GND • n. c. • VIN • VREF
RO2D LI	M4130DIM5-2.0	NS	vref	V _{OUT} = 2.0 B; ACC = 0.4 %; 20 ppm/°C	SOT23-5	n. c. • GND • n. c. • VIN • VREF
ROZE LI	M4130EIM5-2.0	NS	vref	V _{OUT} = 2.0 B; ACC = 0.5 %; 30 ppm/°C	SOT23-5	n. c. • GND • n. c. • VIN • VREF
RO3A LI	M4130AIM5-2.5	NS	vref	V _{OUT} = 2.5 B; ACC = 0.05 %; 10 ppm/°C	SOT23-5	n. c. • GND • n. c. • VIN • VREF
R03B LI	M4130BIM5-2.5	NS	vref	V _{DUT} = 2.5 B; ACC = 0.2 %; 10 ppm/°C	SOT23-5	n. c. • GND • n. c. • VIN • VREF
R03C L	M4130CIM5-2.5	NS	vref	V _{CUT} = 2.5 B; ACC = 0.1 %; 20 ppm/°C	SOT23-5	n. c. • GND • n. c. • VIN • VREF
R03D L	M4130DIM5-2.5	NS	vref	V _{OLIT} = 2.5 B; ACC = 0.4 %; 20 ppm/°C	SOT23-5	n. c. • GND • n. c. • VIN • VREF
R03E LI	M4130EIM5-2.5	NS	vref	V _{OUT} = 2.5 B; ACC = 0.5 %; 30 ppm/°C	SOT23-5	n. c. •GND • n. c. • VIN • VREF
RO4A LI	M4130AIM5-4.1	NS	vref	V _{DLIT} = 4.1 B; ACC = 0.05 %; 10 ppm/°C	SOT23-5	n. c. • GND • n. c. • VIN • VREF
R04B LI	M4130BIM5-4.1	NS	vref	Voir = 4.1 B; ACC = 0.2 %; 10 ppm/°C	SOT23-5	n. c. • GND • n. c. • VIN • VREF
RO4C LI	M4130CIM5-4.1	NS	vref	V _{OLIT} = 4.1 B; ACC = 0.1 %; 20 ppm/°C	SOT23-5	n. c. • GND • n. c. • VIN • VREF
-0.27	M4130DIM5-4.1	NS	vref	V _{CLIT} =4.1B; ACC=0.4%; 20 ppm/°C	SOT23-5	n. c. • GND • n. c. • VIN • VREF
RO4E LI	M4130EIM5-4.1	NS	vref	V _{OUT} = 4.1 B; ACC = 0.5 %; 30 ppm/°C	SOT23-5	n. c. • GND • n. c. • VIN • VREF
ROA A	DR318ARJ	AD	vref	V _{IN} = 2.415 B; I _{DUT} = 5 MA; V _{DUT} = 1.8 B	SOT23-5	SHDN • VIN • VOUTS • -VOUTF • GND
ROA A	DR390AUJZ	AD	vref	V _{IN} = 2.515 B; I _{DUT} = 5 MA; V _{DUT} = 2.048 B	TSOT23-5	SHDN • VIN • VOUTS • VOUTF • GND
ROB A	DR390BUJZ	AD	vref	V _{IN} = 2.515 B; I _{OUT} = 5 MA; V _{OUT} = 2.048 B	TSOT23-5	SHDN • VIN • VOUTS • VOUTF • GND
R1A A	DR391AUJZ	AD	vref	V _{IN} = 2.515 B; I _{DUT} = 5 MA; V _{DUT} = 2.5 B	TSOT23-5	SHDN • VIN • VOUTS • VOUTF • GND
R1B A	DR391BUJZ	AD	vref	V _{IN} = 2.515 B; I _{DUT} = 5 mA; V _{DUT} = 2.5 B	TSOT23-5	SHDN • VIN • VOUTS • VOUTF • GND
R1E A	DR01AKSZ	AD	vref	$V_{IN} = 1240 \text{B}_{i} I_{OUT} = 10 \text{mA}_{i} V_{OUT} = 10 \text{B}$	SOT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
R1E A	DR01AUJZ	AD	vref	V _{IN} = 1240 B; I _{OLIT} = 10 mA; V _{OLIT} = 10 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
R1F A	DR01BKSZ	AD	vref	V _{IN} = 1240 B; I _{OUT} = 10 mA; V _{OUT} = 10 B	SOT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
R1F A	DR01BUJZ	AD	vref	V _{IN} = 1240 B; I _{OUT} = 10 MA; V _{OUT} = 10 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
R1G A	DR02AKSZ	AD	vref	V _{IN} = 740 B; I _{OUT} = 10 mA; V _{OUT} = 5 B	SOT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
R1G A	DR02AUJZ	AD	vref	V _{IN} = 740B; I _{OUT} = 10 mA; V _{OUT} = 5 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
R1H A	DR02BKSZ	AD	vref	V _{IN} = 740B; I _{OUT} = 10 mA; V _{OUT} = 5 B	SOT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
R1H A	DR02BUJZ	AD	vref	V _{IN} = 740B; I _{OUT} = 10 мA; V _{OUT} = 5 В	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
R1J Al	DR03AKSZ	AD	vref	$V_{IN} = 4.540 \text{ B}; I_{DUT} = 10 \text{ mA}; V_{DUT} = 2.5 \text{ B}$	SOT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
R1J A	DR03AUJZ	AD	vref	V _{IN} = 4.540 B; I _{DUT} = 10 mA; V _{DUT} = 2.5 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
R1K A	DR03BKSZ	AD	vref	$V_{IN} = 4.540 \text{ B}; I_{DUT} = 10 \text{ mA}; V_{DUT} = 2.5 \text{ B}$	SOT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
R1K A	DR03BUJZ	AD	vref	V _{IN} = 4.540 B; I _{DUT} = 10 mA; V _{DUT} = 2.5 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
R1L A	DR06AKSZ	AD	vref	V _{IN} =540B; I _{OUT} = 10 mA; V _{OUT} = 3 B	SOT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
R1L A	DR06AUJZ	AD	vref	V _{IN} =540B; I _{OUT} = 10 mA; V _{OUT} = 3 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
R1M A	DR06BKSZ	AD	vref	V _{IN} =540B; I _{OUT} = 10 mA; V _{OUT} = 3 B	SOT353,	TEMP • GND • VIN • VOUT • TRIM
n IM A	DU GODVOT	AU	AIGI	AIN - 9400' 1001 = 10 WH' A001 = 9 D	SC88A	EML - GIAD - AIM - AOO





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5
R1M	ADR06BUJZ	AD	vref	V _{IN} = 540 B; I _{OUT} = 10 mA; V _{OUT} = 3 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
R8A	ADR01AKS	AD	vref	V _{IN} = 1240 B; I _{OUT} = 10 mA; V _{OUT} = 10 B	SOT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
R8A	ADR01AUJ	AD	vref	V _{IN} = 1240 B; I _{OUT} = 10 мA; V _{OUT} = 10 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
R8B	ADR01BKS	AD	vref	V _{IN} = 1240 B; I _{DUT} = 10 mA; V _{DUT} = 10 B	SOT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
R8B	ADR01BUJ	AD	vref	V _{IN} = 1240 B; I _{OUT} = 10 mA; V _{OUT} = 10 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
R9A	ADR02AKS	AD	vref	V _{IN} = 740 B; I _{OUT} = 10 MA; V _{OUT} = 5 B	SOT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
R9A	ADR02AUJ	AD	vref	V _{IN} = 740 B; I _{DUT} = 10 mA; V _{DUT} = 5 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
R9B	ADR02BKS	AD	vref	V _{IN} = 740 B; I _{OUT} = 10 mA; V _{OUT} = 5 B	SOT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
R9B	ADR02BUJ	AD	vref	V _{IN} = 740 B; I _{OUT} = 10 mA; V _{OUT} = 5 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
RCA	ADR392AUJZ	AD	vref	V _{IN} = 2.515 B; I _{OUT} = 5 mA; V _{OUT} = 4.096 B	TSOT23-5	SHDN • VIN • VOUTS • VOUTF • GND
RCB	ADR392BUJZ	AD	vref	V _{IN} = 2.515 B; I _{OUT} = 5 MA; V _{DUT} = 4.096 B	TSOT23-5	SHDN • VIN • VOUTS • VOUTF • GND
RDA	ADR395AUJZ	AD	vref	V _{IN} = 2.515 B; I _{OUT} = 5 mA; V _{OUT} = 5 B	TSOT23-5	SHDN • VIN • VOUTS • VOUTF • GND
RDB	ADR395BUJZ	AD	vref	V _{IN} = 2.515 B; I _{QUT} = 5 mA; V _{DUT} = 5 B	TSOT23-5	SHDN • VIN • VOUTS • VOUTF • GND
RFA	ADR03AKS	AD	vref	V _{IN} = 4.540 B; I _{OUT} = 10 mA; V _{OUT} = 2.5 B	SCT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
RFA	ADR03AUJ	AD	vref	V _{IN} = 4.540 B; I _{OUT} = 10 MA; V _{OUT} = 2.5 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
RFB	ADR03BKS	AD	vref	V _{IN} = 4.540 B; I _{OUT} = 10 mA; V _{OUT} = 2.5 B	SCT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
RFB	ADR03BUJ	AD	vref	V _{IN} = 4.540 B; I _{OUT} = 10 mA; V _{OUT} = 2.5 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
RWA	ADR06AKS	AD	vref	V _{IN} = 540 B; I _{OUT} = 10 mA; V _{OUT} = 3 B	SOT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
RWA	ADR06AUJ	AD	vref	V _{IN} = 540 B; I _{OUT} = 10 mA; V _{OUT} = 3 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
RWB	ADR06BKS	AD	vref	V _{IN} = 540 B; I _{OUT} = 10 mA; V _{OUT} = 3 B	SOT353, SC88A	TEMP • GND • VIN • VOUT • TRIM
RWB	ADR06BUJ	AD	vref	V _{IN} = 540 B; I _{OUT} = 10 mA; V _{OUT} = 3 B	TSOT23-5	TEMP • GND • VIN • VOUT • TRIM
S00	ADG741BKSZ5	AD	asw	2xSPST; R _{ON} < 4 OM; V _{DD} = 1.85.5 B	SOT353, SC88A	D • S • GND • IN • VDD
S01	ADG742BKSZ5	AD	asw	$2 \times SPST; R_{ON} < 4 Om; V_{DD} = 1.85.5 B$	SOT353, SC88A	D • S • GND • IN • VDD
S1	EMS1	ROHM	рпр х2	$V_{CBD} = 60 \text{ B; } I_C = 150 \text{ mA; } P_D = 150 \text{ mBt; } h_{21} > 120$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
S1	FMS1A	100000	pnp x2	$V_{CBD} = 60 \text{ B}; I_C = 150 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 120$	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
S1	UMS1N	ROHM	pnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D (com.) = 300 mBT; h_{21} > 120	SC88A	B1 • E1, E2 • B2 • C2 • C1
S2	FMS2A		pnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} > 120$	SOT23-5	C1 • C2 • E2 • B1, B2 • E1
S2	UMS2N	ROHM	рпр х2	$V_{CBD} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D(\text{com.}) = 300 \text{ mBT; } I_{21} > 120$	SC88A	E1 • B1, B2 • E2 • C2 • C1
S3	FMS3		pnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ MA}; P_D = 300 \text{ MBT}; h_{21} > 120$	SOT23-5	C2 • E1, E2 • C1 • B1 • B2
S3B	ADG701BRJ	AD	asw	SPST; R _{ON} < 4 O _M ; V _{DD} = 1.85.5 B	SOT23-5	D • S • GND • IN • VDD
S4	FMS4		pnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 120$	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
S47	OPA347SA	TI	OA	R-R; V_{DD} = 2.35.5 B; f_{BD} = 350 kFu; I_S = 43 kKA; V_{DS} < 7 kB	SOT353, SC88A	+IN • V- • -IN • OUT • V+
S48	OPA348AI	TI	OA	R-R; V_{DD} = 2.15.5 B; f_{BD} = 1 MFu; I_S = 75 mrA; V_{DSI} < 6 mB	SOT353, SC88A	+IN • V- • -IN • OUT • V+
S4B	ADG702BRJ	AD	asw	SPST; R _{DN} < 4 O _M ; V _{DD} = 1.85.5 B	SOT23-5	D • S • GND • IN • VDD
T2B	LM20BIM7	NS	ats	T _{AMB} = -55130 °C; V _{CC} = 2.45.5 B; I _{OUT} < 10 mA	SOT353, SC88A	n. c. ● GND ● Vo ● GND ● V+
T2C	LM20CIM7	NS	ats	T _{AMB} = -55130 °C; V _{CC} = 2.45.5 B; I _{OUT} < 10 mA	SOT353, SC88A	n. c. • GND • Vo • GND • V+



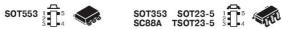


Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1+2+3+4+5
T5G	TMP35GRT	AD	ats	T _{AMB} = 10125 °C; V _{CC} = 2.75.5 B; I _{OUT} < 50 mkA; ACC = ± 3°C	SOT23-5	VOUT • +VS • n. c. • SHDN • GND
T6G	TMP36GRT	AD	ats	T _{AMB} =-40125'C; V _{CC} =2.75.5B; I _{DUT} <50 mKA; ACC=±3'C	SOT23-5	VOUT • +VS • n. c. • SHDN • GND
T7G	TMP37GRT	AD	ats	T _{AMB} =5100 °C; V _{CC} =2.75.5 В; I _{DUT} < 50 мкА; ACC = ±3°C	SOT23-5	VOUT • +VS • n. c. • SHDN • GND
VO	MC74VHC1G01DF	ON	2-NAND	V _{CC} =2.05.5B; t _{PD} =3.7 HC	SOT353, SC88A	INB • INA • GND • OUTY • VCC
VO	MC74VHC1G01DT	ON	2-NAND	V _{CC} =2.05.5B; t _{PD} =3.7 HC	SOT23-5	INB • INA • GND • OUTY • VCC
V3	MC74VHC1G02DF	ON	2-NOR	V _{CC} =2.05.5 В; t _{PD} =3.0 нс	SOT353, SC88A	INB • INA • GND • OUTY • VCC
VA	MC74VHC1G14	ON	Schminv	V _{CC} =2.05.5B; t _{PD} =4.5 HC	SOT23-5	n. c. • INA • GND • OUT Y • VCC
VAZI	TLV2631IDBV	TI	OA	R-R; V _{DD} =2.75.5 B; f _{BD} =9 MFu; V _{DS} <4.5 MB	SOT23-5	OUT • GND • IN+• IN • VDD
VC	MC74VHC1GT14DF	ON	Schminv	V _{CC} =3.05.5В; t _{PD} =4.5 нс	SOT353, SC88A	n. c. • INA • GND • OUT Y • VCC
VC	MC74VHC1GT14DT	ON	Schminv	V _{CC} =3.05.5B; t _{PD} =4.5 HC	SOT23-5	n. c. • INA • GND • OUT Y • VCC
VD	MC74VHC1G132DF	ON	SchmNAND	V _{CC} =2.05.5 B; t _{PD} =3.6 HC	SOT353, SC88A	INB • INA • GND • OUTY • VCC
VD	MC74VHC1G132DT	ON	SchmNAND	V _{cc} =2.05.5 В; t _{PD} =3.6 нс	SOT23-5	INB • INA • GND • OUTY • VCC
VT	MC74VHC1GT08DF	ON	2-AND	V _{CC} =3.05.5 B ; t _{PD} =3.5 Hc	SOT353, SC88A	INB • INA • GND • OUTY • VCC
VT	MC74VHC1GT08DT	ON	2-AND	V _{CC} =3.05.5В; t _{PD} =3.5 нс	SOT23-5	INB • INA • GND • OUT Y • VCC
VU	MC74VHC1GT132DF	MOT	SchmNAND	V _{CC} =3.05.5B; t _{PD} =3.6 Hc	SOT353, SC88A	INB • INA • GND • OUTY • VCC
VU	MC74VHC1GT132DT	MOT	SchmNAND	V _{CC} =3.05.5В; t _{PD} =3.6 нс	SOT23-5	INB • INA • GND • OUT Y • VCC
VX	MC74VHC1G09DF	ON	2-AND	V _{CC} =2.05.5В; t _{PD} =4.3 нс	SOT353, SC88A	INB • INA • GND • OUTY • VCC
VZ	MC74VHC1G135DF	ON	SchmNAND	V _{CC} =2.05.5В; t _{PD} =4.9 нс	SOT353, SC88A	INB • INA • GND • OUTY • VCC
VZ	MC74VHC1G135DT	ON	SchmNAND	V _{CC} =2.05.5 В; t _{PD} =4.9 нс	SOT23-5	INB • INA • GND • OUT Y • VCC
W0	MC74VHC1G125DF	ON	3-stbuff	V _{CC} =2.05.5 В; t _{PD} =3.5 нс	SOT353, SC88A	OE • INA • GND • OUT Y • VCC
WO		ON	3-stbuff	V _{CC} =2.05.5 В; t _{PD} =3.5 нс	SOT23-5	OE • INA • GND • OUT Y • VCC
W1	FMW1		npn x2	$V_{CB0} = 60 \text{ B}; I_C = 150 \text{ mA}; P_D = 300 \text{ mB}\text{T}; h_{21} > 120$	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
W1	MC74VHC1GT125DF	ON	3-stbuff	V _{CC} =3.05.5 В; t _{PD} =3.5 нс	SOT353, SC88A	CE◆INA◆GND◆OUT Y ◆VCC
W1		ON	3-stbuff	V _{CC} =3.05.5 B; t _{PD} =3.5 нс	SOT23-5	OE • INA • GND • OUT Y • VCC
W1	UMW1N	ROHM	npn x2	$V_{CB0} = 50 \text{B}; I_C = 100 \text{ mA}; P_D \text{ (com.)} = 300 \text{ mBT}; h_{21} = 180560$	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
W11	UMW11N	ROHM	npn x2	V_{CB0} =30B; I_C =50mA; P_D (com.)=300mBT; h_{21} =27270; f_T >1500M Γ_{IJ}	SOT353, SC88A	E1 • B1, B2 • E2 • C2 • C1
W12	UMW12N	ROHM	npn x2	V_{CB0} = 50B; I_C = 100 mA; P_D (com.) = 300 mBT; I_{21} > 120	SOT353, SC88A	E1, C2 • C1 • B1 • B2 • E2
W13	UMW13N	ROHM	npn x2	V_{CB0} =30B; I_C =50mA; P_D (com.)=300mBT; h_{21} =27270; f_T >2000MFu	SOT353, SC88A	E1 • B1, B2 • E2 • C2 • C1
W2	FMW2		npn x2	$V_{CB0} = 60 \text{ B}; I_C = 150 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 120$	SOT23-5	C1 • C2 • E2 • B1, B2 • E1
W2	MC74VHC1G126DF	ON	3-stbuff	V _{CC} =2.05.5 В; t _{PD} =3.5 нс	SOT353, SC88A	OE • INA • GND • OUT Y • VCC
W2		ON	3-stbuff	V _{CC} =2.05.5 В; t _{PD} =3.5 нс	SOT23-5	OE • INA • GND • OUT Y • VCC
W2	UMW2N	ROHM	npn x2	V_{CB0} = 50B; I_C = 100 mA; P_D (com.) = 300 mBT; h_{21} > 120	SOT353, SC88A	E1 • B1, B2 • E2 • C2 • C1
W3	FMW3		npn x2	$V_{CB0} = 120 \text{ B}; I_C = 50 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 180$	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
W3	MC74VHC1GT126DF		3-stbuff	V _{CC} =3.05.5В; t _{PD} =3.5 нс	SOT353, SC88A	OE • INA • GND • OUT Y • VCC
W3	MC74VHC1GT126DT	ON	3-stbuff	V _{CC} =3.05.5 В; t _{PD} =3.5 нс	SOT23-5	OE • INA • GND • OUT Y • VCC
W4	FMW4	ROHM	npn x2	$V_{CB0} = 120 \text{ B}; I_C = 50 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 180$	SOT23-5	C1 • C2 • E2 • B1, B2 • E1





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1+2+3+4+5
W5	UMW5N	ROHM	npn x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D(\text{com.}) = 300 \text{ mBT}; h_{21} > 250$	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
N 6	FMW6	ROHM	npn x2	$V_{CB0} = 30 \text{ B; } I_C = 50 \text{ mA; } P_D = 300 \text{ mBr; } h_{21} > 27$	SOT23-5	C2,E1 • C1 • B1 • B2 • E2
W6	UMW6N	ROHM	npn x2	$V_{CB0} = 30 \text{ B}; I_C = 50 \text{ mA}; P_D \text{ (com.)} = 300 \text{ mBT}; h_{21} = 27270; f_T > 1500 \text{ MFu}$	SOT353, SC88A	E2 • B2 • B1 • C1 • E1, C2
₩7	FMW7	ROHM	npn x2	$V_{CB0} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D = 300 \text{ mBr; } h_{21} > 27$	SOT23-5	C1,E2 • C2 • B2 • B1 • E1
W7	UMW7N	ROHM	npn x2	$V_{CBD} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D \text{ (com.)} = 300 \text{ mBT;} h_{21} = 27270; f_T > 3200 \text{ MFu}$	SOT353, SC88A	E2 • B2 • B1 • C1 • E1, C2
W8	UMW8N	ROHM	npn x2	$V_{CB0} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D \text{ (com.)} = 300 \text{ mBT; } I_{21} = 27270; I_T > 3200 \text{ MF II}.$	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
W9	UMW9T	ROHM	npn x2	V_{CB0} = 20 B; I_C = 50 mA; P_D (com.) = 300 mBT; h_{21} = 27 270; f_T > 3200 MFu	SOT353, SC88A	E1 • B1, B2 • E2 • C2 • C1
XA	RN1501	TOSH	Dnpn x2	V _{CBD} =50 B; I _C =100 мА; P _D =300 мВт; f _T =250 МГц; R ₁ /R ₂ =4.7 кОм/4.7 кОм	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
XA	RN1701	TOSH	Dnpn x2	V _{CBD} =50 B; I _C =100 мA; P _D =200 мBт; f _T =250 MFц; R ₁ /R ₂ =4.7 кОм/4.7 кОм	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
XA	RN1701JE	TOSH	Dnpn x2	V _{CB0} =50 B; I _C =100 mA; P _D =100 mBt; f _T =250 MFu; R ₁ /R ₂ =4.7 kOm/4.7 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
XB	RN1502	TOSH	Dnpn x2	V _{CB0} =50 B; I _C =100 мA; P _D =300 мВт; f _T =250 МГц; R ₁ /R ₂ =10 кОм/10 кОм	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
XB	RN1702	TOSH	Dnpn x2	V _{CB0} = 50 B; I _C = 100 мA; P _D = 200 мВт; f _T = 250 МГц; R ₁ /R ₂ = 10 кОм/10 кОм	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
XB	RN1702JE	TOSH	Dnpn x2	$V_{CBD} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBr; } I_T = 250 \text{ MFu; } R_1/R_2 = 10 \text{ kOm}/10 \text{ kOm}$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
XC	RN1503	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 300 \text{ mB} \text{ T}; f_T = 250 \text{ MF L}; R_1/R_2 = 22 \text{ KOM}/22 \text{ KOM}$	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
XC	RN1703	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBt; f_T = 250 MFu; R_1/R_2 = 22 kOm/22 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
XC	RN1703JE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBt; } I_T = 250 \text{ MFu; } R_1/R_2 = 22 \text{ kOm}/22 \text{ kOm}$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
XD	RN1504	TOSH	Dnpn x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 300 mB1; f_T = 250 MFu; P_S = 47 kOm/47 kOm	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
XD	RN1704	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mB}\tau; f_T = 250 \text{ MF}\iota; R_1/R_2 = 47 \text{ KOm}/47 \text{ KOM}$	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
XD	RN1704JE	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 100 mBt; f_T = 250 MFu; R_1/R_2 = 47 kOm/47 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
XE	RN1505	TOSH	Dnpn x2	V _{CB0} =50 B; I _C =100 мA; P _D =300 мВт; f _T =250 МГц; R ₁ /R ₂ =2.2 кОм/47 кОм	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
XE	RN1705	TOSH	Dnpn x2	V _{CBD} =50 B; I _C =100 мА; P _D =200 мВт; f _T =250 МГц; R ₁ /R ₂ =2.2 кОм/47 кОм	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
XE	RN1705JE	TOSH	Dnpn x2	V _{CBD} =50 B; I _C =100 mA; P _D =100 mBt; f _T =250 MFu; R ₁ /R ₂ =2.2 kOm/47 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
XF	RN1506	TOSH	Dnpn x2	V _{CB0} =50 B; I _C =100 mA; P _D =300 mBt; f _T =250 MFu; R ₁ /R ₂ =4.7 kOm/47 kOm	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
XF	RN1706	TOSH	Dnpn x2	V _{CB0} =50 B; I _C =100 мA; P _D =200 мВт; f _T =250 МГц; R ₁ /R ₂ =4.7 кОм/47 кОм	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
XF	RN1706JE	TOSH	Dnpn x2	V _{CBD} = 50 B; I _C = 100 мА; P _D = 100 мВт; f _T = 250 МГц; R ₁ /R ₂ = 4.7 кОм/47 кОм	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
XH	RN1507	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBr; } I_T = 250 \text{ MFr; } I_R = 10 \text{ kOm}/47 \text{ kOm}$	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
XH	RN1707	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBt; } f_T = 250 \text{ MFI; } R_1/R_2 = 10 \text{ kGm}/47 \text{ kGm}$	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
XH	RN1707JE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } I_T = 250 \text{ MFL; } R_1/R_2 = 10 \text{ kOm}/47 \text{ kOm}$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
XI	RN1508	TOSH	Dnpn x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 300 mB1; f_T = 250 MF1; R_1/R_2 = 22 kOm/47 kOm	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
XI	RN1708	TOSH	Dnpn x2	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBt; f _T =250 MFu; R ₁ /R ₂ =22 kOm/47 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1+2+3+4+5
ď	RN1708JE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } I_T = 250 \text{ MFu; } R_1/R_2 = 22 \text{ kOm}/47 \text{ kOm}$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
(J	RN1509	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBT; } I_T = 250 \text{ MFu; } I_1/R_2 = 47 \text{ kOm/} 22 \text{ kOm}$	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
U	RN1709	TOSH	Dnpn x2	V_{CB0} =50B; I_C =100mA; P_D =200mBt; f_T =250M Γ_{LI} ; R_1/R_2 =47kOm/22kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
U	RN1709JE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 100 \text{ mB}\tau; f_T = 250 \text{ MFu}; R_1/R_2 = 47 \text{ kOm}/22 \text{ kOm}$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
(K	RN1510	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 300 mB1; I_T = 250 MFu; I_T = 4.7 kOm	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
(K	RN1710	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; f_T = 250 MFu; R_1 = 4.7 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
(K	RN1710JE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 100 \text{ mBT}; f_T = 250 \text{ MFu}; R_1 = 4.7 \text{ kOm}$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
M	RN1511	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 300 \text{ mBT}; f_T = 250 \text{ MFu}; R_1 = 10 \text{ kOm}$	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
M	RN1711	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } $ $f_T = 250 \text{ MFu; } R_1 = 10 \text{ kOm}$	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
(M	RN1711JE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 100 \text{ mBT}; I_T = 250 \text{ MFu}; R_1 = 10 \text{ kOm}$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
/1	EMY1	ROHM	npn+pnp	$V_{CB0} = 60B$; $I_C = 150 \text{ mA}$; $P_D = 300 \text{ mBT}$; $h_{21} > 120$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
/1	FMY1A	ROHM	npn+pnp	$V_{CB0} = 60 \text{ B}; I_C = 150 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 120$	SOT23-5	C1 • C2 • B2 • E1, E2 • B1
/1	UMY1N	ROHM	pnp(1)+npn (2)	$V_{CB0} = 50B$; $I_C = 100 \text{ mA}$; $P_D \text{ (com.)} = 300 \text{ mB}\text{T}$; $h_{21} > 120$; $f_T > 180 \text{ MFu}$	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
3	FMY3A	ROHM	npn+pnp	$V_{CB0} = 60B$; $I_C = 150 \text{ mA}$; $P_D = 300 \text{ mBT}$; $h_{21} > 120$	SOT23-5	C1 • C2 • E2 • B2, E1 • B1
′3	UMY3N	ROHM	pnp(1)+npn (2)	$V_{CB0} = 50B$; $I_C = 100 \text{ mA}$; $P_D (com.) = 300 \text{ mBT}$; $h_{21} = 120560$; $f_T > 180 \text{ MFu}$	SOT353, SC88A	B1 • E1, B2 • E2 • C2 • C1
/4	FMY4A		прп+рпр	$V_{CB0} = 60B$; $I_C = 150 \text{ mA}$; $P_D = 300 \text{ mB} \text{ T}$; $h_{21} > 120$	SOT23-5	C1 • C2 • B2 • B1, E2 • E1
/4	UMY4N	ROHM	pnp(1)+npn (2)	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D (\text{com.}) = 300 \text{ mB} \text{ T}; h_{21} = 120560; f_T > 180 \text{ MFL}$	SOT353, SC88A	E1 • B1, E2 • B2 • C2 • C1
/ 5	FMY5	ROHM	npn+pnp	$V_{CB0} = 120 \text{ B; } I_C = 50 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} > 120$	SOT23-5	C1 • C2 • B2 • E1, E2 • B2
6	FMY6	ROHM	npn+pnp	$V_{CB0} = 40B$; $I_C = 500 \text{ mA}$; $P_D = 300 \text{ mB}\text{T}$; $h_{21} > 120$	SOT23-5	C1 • C2 • B2 • E1, E2 • B2
/A	RN2501	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 300 \text{ mB}\tau; f_T = 200 \text{ MFu}; R_1/R_2 = 4.7 \text{ kOm}/4.7 \text{ kOm}$	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
ſΑ	RN2701	TOSH	Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; f_T = 200 MFu; R_1/R_2 = 4.7 kOm/4.7 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
ſΑ	RN2701JE		Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 100 mB r; f_T = 200 MFu; R_1/R_2 = 4.7 kOm/4.7 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
/B	RN2502	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 300 \text{ mB} \text{ T}; f_T = 200 M \Gamma u; R_1/R_2 = 10 k O m / 10 k O m$	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
/B	RN2702	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mB}\text{T}; f_T = 200 \text{ MFu}; R_1/R_2 = 10 \text{ kOm}/10 \text{ kOm}$	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
/B	RN2702JE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 100 \text{ mB}\text{T}; f_T = 200 M \Gamma u; R_1/R_2 = 10 k O m / 10 k O m$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
(C	RN2503	100111111111111111111111111111111111111	Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 300 mBT; I_T = 200 MFu; I_T $I_$	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
rC	RN2703	0.000.00	Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; f_T = 200 MFц; R_1/R_2 = 22 kOm/22 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
/C	RN2703JE	1000000000	Dpnp x2	$V_{CB0} = 50 \text{B}; I_C = 100 \text{mA}; P_D = 100 \text{mBT}; f_T = 200 \text{MFu}; R_1/R_2 = 22 \text{kOm}/22 \text{kOm}$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
/D	RN2504	1000000000	Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 300 mBT; f_T = 200 MFL; R_1/R_2 = 47 kOm/47 kOm	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
/D	RN2704	-27/03/03/03	Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; f_T = 200 MFu; R_1/R_2 = 47 kOm/47 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
/D	RN2704JE		Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 100 mBT; f_T = 200 MFц; R_1/R_2 = 47 кOm/47 кOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
Έ	RN2505	TOSH	Dрпр x2	$V_{CB0} = 50 B_1 I_C = 100 \text{ mA}; P_D = 300 \text{ mBT}; f_T = 200 MFu; R_1/R_2 = 2.2 kOm/47 kOm$	SOT23-5	B1 • E1, E2 • B2 • C2 • C1





Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3•4•5
YE	RN2705	TOSH	Dpnp x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 200 mB1; f_T = 200 MF1; I_C = 2.2 kOm/47 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
YE	RN2705JE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBt; } I_T = 200 \text{ MFu; } I_1/R_2 = 2.2 \text{ KOm}/47 \text{ KOm}$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
YF	RN2506	TOSH	Dрпр x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 300 \text{ mBt}; f_T = 200 \text{ MFL}; R_1/R_2 = 4.7 \text{ KOM}/47 \text{ KOM}$	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
YF	RN2706	TOSH	Dpnp x2	$V_{CBD} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBt; } f_T = 200 \text{ MFu; } R_1/R_2 = 4.7 \text{ kGm}/47 \text{ kGm}$	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
YF	RN2706JE	TOSH	Dpnp x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 100 mBt; f_T = 200 MFu; R_1/R_2 = 4.7 kOm/47 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
YH	RN2507	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 300 \text{ mBT}; f_T = 200 \text{ MFL}; R_1/R_2 = 10 \text{ KOm}/47 \text{ KOM}$	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
YH	RN2707	TOSH	Dpnp x2	V _{CB0} =50B; I _C =100 мA; P _D =200 мВт; f _T =200 МГц; R ₁ /R ₂ =10 кОм/47 кОм	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
ΥH	RN2707JE	TOSH	Dpnp x2	V _{CB0} =50 B; I _C =100 мA; P _D =100 мВт; f _T =200 МГц; R ₁ /R ₂ =10 кОм/47 кОм	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
ΥI	RN2508	TOSH	Dpnp x2	V _{CBD} =50 B; I _C =100 мА; P _D =300 мВт; f _T =200 МГц; R ₁ /R ₂ =22 кОм/47 кОм	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
ΥI	RN2708	TOSH	Dрпр x2	V _{CB0} =50 B; I _C =100 mA; P _D =200 mBt; f _T =200 MFu; R ₁ /R ₂ =22 kOm/47 kOm	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
ΥI	RN2708JE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 100 \text{ mBt}; f_T = 200 \text{ MFu}; R_1/R_2 = 22 \text{ kOm}/47 \text{ kOm}$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
YJ	RN2509	TOSH	Dpnp x2	V _{CB0} =50 B; I _C =100 мА; P _D =300 мВт; f _T =200 МГц; R ₁ /R ₂ =47 кОм/22 кОм	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
YJ	RN2709	TOSH	Dpnp x2	$V_{CBD} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mB}\tau; f_T = 200 \text{ MFL}; R_1/R_2 = 47 \text{ KOm}/22 \text{ KOm}$	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
YJ	RN2709JE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 100 \text{ mBt}; f_T = 200 \text{ MFu}; R_1/R_2 = 47 \text{ kOm}/22 \text{ kOm}$	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
YK	RN2510	TOSH	Dpnp x2	V _{CB0} =50 B; I _C =100 мA; P _D =300 мВт; f _T =200 МГц; R ₁ =4.7 кОм	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
YK	RN2710	TOSH	Dpnp x2	V _{CBD} =50 B; I _C =100 мA; P _D =200 мВт; f _T =200 МГц; R ₁ =4.7 кОм	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
YK	RN2710JE	TOSH	Dpnp x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 100 mBT; f_T = 200 MFu; P_D = 4.7 kOm	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
YM	RN2511	TOSH	Dрпр x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBT; } f_T = 200 \text{ MFu; } R_1 = 10 \text{ kOm}$	SOT23-5	B1 • E1, E2 • B2 • C2 • C1
YM	RN2711	TOSH	Dрпр x2	V _{CB0} =50 B; I _C =100 мА; P _D =200 мВт; f _T =200 МГц; R ₁ =10 кОм	SOT353, SC88A	B1 • E1, E2 • B2 • C2 • C1
YM	RN2711JE	TOSH	Dрпр x2	V _{CBD} =50 B; I _C =100 мА; P _D =100 мВт; f _T =200 МГц; R ₁ =10 кОм	SOT553, EMT5	B1 • E1, E2 • B2 • C2 • C1
Z25	NC7SZ125P5X	FAIR	3-stbuff	V _{CC} = 1.655.5B; I _{OUT} = ± 24 мA	SOT353, SC88A	OE • A • GND • Y • VCC





SOT23-6, SOT363/563...

Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
11	MUN5311DW1	ON	Dnpn/pnp	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 35; \\ 10 \text{ kOm}/10 \text{ kOm}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
12	MUN5312DW1	ON	Dnpn/pnp	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBt; } h_{21} > 60; 22 \text{ kOm}/22 \text{ kOm}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
13	MUN5313DW1	ON	Dnpn/pnp	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mB1; h_{21} > 80; 47 кOm/47 кOm	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
14	MUN5314DW1	ON	Dnpn/pnp	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBt; } h_{21} > 80; \\ 10 \text{ KOm}/47 \text{ kOm}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
15	MUN5315DW1	ON	Dnpn/pnp	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBt; } h_{21} > 160; \\ R_1 = 10 \text{ kOm}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
16	MUN5316DW1	ON	Dnpn/pnp	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBt; h_{21} > 160; R_1 4.7 kOm	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
30	MUN5330DW1	ON	Dnpn/pnp	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBr; } h_{21} > 3;$ 1 kOm/1 kOm	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
31	MUN5331DW1	ON	Dnpn/pnp	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; h_{21} > 8; 2.2 kOm/2.2 kOm	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
32	MUN5332DW1	ON	Dnpn/pnp	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mB τ ; h_{21} > 15; 4.7 kOm/4.7 kOm	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
33	MUN5333DW1	ON	Dnpn/pnp	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; h_{21} > 80; 4.7 kOm/47 kOm	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
34	MUN5334DW1	ON	Dnpn/pnp	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 80; \\ 22 \text{ KOm}/4.7 \text{ KOM}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
35	MUN5335DW1	ON	Dnpn/pnp	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 80; \\ 2.2 \text{ KOM}/4.7 \text{ KOM}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
#CHA	AD7414ARTZ	AD	dts	10-pasp.; SMBus/I ² C; V _{DD} =2.75.5B	SOT23-6	AS • GND • VDD • SCL • ALERT • SDA
0A	NSBA114EDXV6	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBT; } h_{21} > 35; \\ 10 \text{ kOm}/10 \text{ kOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
0A	MUN5111DW1	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 35; \\ 10 \text{ KOm}/10 \text{ kOm}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
0B	NSBA124EDXV6	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBt; } h_{21} > 60; \\ 22 \text{ KOm}/22 \text{ KOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
0B	MUN5112DW1	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 60; \\ 22 \text{ KOm}/22 \text{ KOm}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
OC	NSBA144EDXV6	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBt; } h_{21} > 80; \\ 47 \text{ KOm}/47 \text{ KOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
OC	MUN5113DW1	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBt; } h_{21} > 80; $ $47 \text{ кOm}/47 \text{ кOm}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
0D	NSBA114YDXV6	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBt; } h_{21} > 80; \\ 10 \text{ KOm}/47 \text{ KOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
OD.	MUN5114DW1	ON	D pпр x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 80; \\ 10 \text{ KOm}/47 \text{ KOm}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
0E	NSBA114TDXV6	ON	Dpпр x2	$V_{CB0} = 50 \text{B}; I_C = 100 \text{mA}; P_D = 357 \text{mB} \tau; h_{21} > 160; R_1 10 \text{κOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
0E	MUN5115DW1	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 160; \\ R_1 10 \text{ kCm}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
0F	NSBA143TDXV6	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBt; } h_{21} > 160; \\ R_1 4.7 \text{ kOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
0F	MUN5116DW1	ON	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} > 160; R_1 4.7 \text{ kOM}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
0G	MUN5130DW1	ON	Dpnp x2	$V_{CB0} = 50 B; I_C = 100 \text{mA}; P_D = 200 \text{mB}\tau; h_{21} > 3; 1 \text{kOm}/1 \text{kOm}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
0G	NSBA113EDXV6	ON	Dpnp x2	V _{CB0} = 50 B; I _C = 100 mA; P _D = 357 mBT; h ₂₁ > 3; 1 kOm/1 kOm	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2



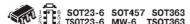


Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
H	NSBA123EDXV6	ON	Dpnp x2	V_{CB0} =50 B; I_C =100 mA; P_D =357 mBT; h_{21} >8; 2.2 KOm/2.2 KOm	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
OH	MUN5131DW1	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBt; } h_{21} > 8; \\ 2.2 \text{ KOm}/2.2 \text{ KOm}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
OJ.	NSBA143EDXV6	ON	Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 357 mBT; h_{21} > 15; 4.7 kOm/4.7 kOm	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
OJ.	MUN5132DW1	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 15; \\ 4.7 \text{ kOm}/4.7 \text{ kOm}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
Ж	NSBA143ZDXV6	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBT; } h_{21} > 80; 4.7 \text{ kOm}/47 \text{ kOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
OK	MUN5133DW1	ON	Dрпр x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 80; 4.7 \text{ KOM}/47 \text{ KOM}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
DL	NSBA124XDXV6	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBT; } h_{21} > 80; $ $22 \text{ KOm}/47 \text{ KOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
OL	MUN5134DW1	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 80; 22 \text{ kOm}/4.7 \text{ kOm}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
OM	NSBA123JDXV6	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBT; } h_{21} > 80; 2.2 kOm/4.7 kOm$	EMT6	E2 • B2 • C1 • E1 • B1 • C2
OM	MUN5135DW1	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBt; } h_{21} > 80; 2.2 kOm/4.7 kOm$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
ON	MUN5136DW1	ON	Dpnp x2	V_{DB0} =50 B; I_C =100 mA; P_D =200 mBT; h_{21} >80; 100 kOm/100 kOm	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
ON	NSBA115EDXV6	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBt; } h_{21} > 80; \\ 100 \text{ kOm} / 100 \text{ kOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
OP	MUN5137DW1	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 80; $ 47 kOm/22 kOm	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
OP	NSBA144WDXV6	ON	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBT; } h_{21} > 80; $ 47 kOm/22 kOm	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
100	NMT2222	NS	npn	V _{CB0} =75 B; I _C =1 A; h ₂₁ >35; f _T >300МГц	SOT23-6	B1 • E2 • B2 • C2 • E1 • C1
1000	ZXTS1000E6	ZETEX	pnp+ shd	V _{CEO} = 12 B; I _C = 1.25 A; V _R = 40 B; I _F = 0.5 A	SOT23-6	C • E • K • A • n. c. • B1
11	NSBC114EPDXV6	ON	Dnpn/pnp	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_0 = 357 \text{ mBt; } h_{21} > 35; \\ 10 \text{ kOm}/10 \text{ kOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
11	RN46A1	TOSH	Dpnp/npn	V _{CB0} =50 B; I _C =100 MA; P _D =300 MBT; Q1: R ₁ /R ₂ =22 kOm/22 kOm; Q2: R ₁ /R ₂ =10 kOm/10 kOm	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
12	NSBC124EPDXV6	ON	Dnpn/pnp	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBT; } h_{21} > 60; $ $22 \text{ kOm}/22 \text{ kOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
13	NSBC144EPDXV6	ON	Dnpn/pnp	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBT; } h_{21} > 80; $ $47 \text{ KOm}/47 \text{ KOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
14	NSBC114YPDXV6	ON	Dnpn/pnp	$V_{DB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBT; } h_{21} > 80; \\ 10 \text{ k/Om}/47 \text{ k/Om}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
15	NSBC114TPDXV6	ON	Dnpn/pnp	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_0 = 357 \text{ mBT; } h_{21} > 160; \\ R_1 10 \text{ kOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
15	RN49A1	TOSH	Dpnp/npn	V _{CBD} =50 B; I _C =100 MA; P _D =200 MBT; Q1: B ₁ /B ₂ =2.2 kOM/47 kOM; Q2: B ₁ /B ₂ =22 kOM/47 kOM	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
16	MT6L61AFS	TOSH	npn x2	$V_{CB0} = 5 B; I_C = 25/40 \text{ mA}; P_D = 50 \text{ mBT}; f_T > 7 \Gamma \Gamma I,$	fS6	B2 • E2 • B1 • C1 • E1 • C2
16	NSBC143TPDXV6	ON	Dnpn/pnp	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBt; } h_{21} > 160; \\ R_1 4.7 \text{ kOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
17	MT6L62AFS	TOSH	npn x2	$V_{CB0} = 5 \text{ B; } I_C = 25/40 \text{ mA; } P_D = 50 \text{ mBT; } f_T > 10 \Gamma \Gamma_H$	fS6	B2 • E2 • B1 • C1 • E1 • C2
17B	RN4962FE	TOSH	Dpnp/npn	$V_{DB0} = 50 B_1 I_D = 100 \text{mA}_1 P_D = 100 \text{mB}_T; f_T = 200 \text{MFu}_1; R_1/R_2 = 10 \text{kOm}/10 \text{kOm}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
1 B s	BC817UPN	INF	npn/pnp	V_{CB0} = 50 B; I_C = 500 mA; P_D = 330 mBT; h_{21} = 160400; f_T = 170 M $\Gamma_{\rm L}$	SOT457, SC74	E1 • B1 • C2 • E2 • B2 • C1
1Cs	BC847S	INF	npn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 250 mBT; h_{21} = 110630; f_T = 250 M Γ_{LI}	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
1Ds	BC846U	INF	npn x2	$V_{CB0} = 80 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBT; } $ $h_{21} = 200450; f_T = 250 \text{ MFu}$	SOT457, SC74	E1 • B1 • C2 • E2 • B2 • C1





Код			Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6	
10s	BC846PN	INF	pnp/npn	$V_{CB0} = 80 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBT; } h_{21} = 200450; f_T > 100 \text{ MFц}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1	
Ps	BC847PN	INF	pnp/npn	V_{CB0} = 50 B; I_C = 100 мA; P_D = 250 мВт; h_{21} = 110630; f_T = 250 МГц	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1	
24R	μPA810T	NEC	npn x2	V_{CB0} = 20 B; I_C = 100 mA; P_D = 230 mBt; h_{21} = 70140; f_T > 3 $\Gamma\Gamma I_L$	SC88	C1 • E1 • C2 • E2 • B2 • B1	
25R	μPA810T	NEC	npn x2	V_{CB0} = 20 B; I_C = 100 mA; P_D = 230 mBr; h_{21} = 110240; f_T > 3 $\Gamma\Gamma r_L$	SC88	C1 • E1 • C2 • E2 • B2 • B1	
28	RN49A2	TOSH	Dpnp/npn	$\Omega_1^{12}: R_1/R_2 = 47 \text{ KOM}/47 \text{ KOM};$ $\Omega_2^{12}: R_1/R_2 = 2.2 \text{ KOM}/47 \text{ KOM}$		E1 • B1 • C2 • E2 • B2 • C1	
N02	ZXM62N02E6	ZETEX	nMOS	R _{DS(on)} < 0.1250 _M		D•D•G•S•D•D	
30	NSBC113EPDXV6	ON	Dnpn/pnp	V_{CB0} = 50 B; I_C = 100 mA; P_D = 357 mBt; h_{21} > 3; SOT5(EMT6		E2 • B2 • C1 • E1 • B1 • C2	
31	NSBC123EPDXV6	ON	Dnpn/pnp	V_{CB0} = 50 B; I_C = 100 mA; P_D = 357 mBt; h_{21} > 8; SOT563, EMT6		E2 • B2 • C1 • E1 • B1 • C2	
32	NSBC143EPDXV6	I BACK	Dnpn/pnp	4.7 KOM/4.7 KOM			
33	NSBC143ZPDXV6	1866	Dnpn/pnp	V _{CB0} = 50 B; I _C = 100 мА; P _D = 357 мВт; h ₂₁ > 80; SOT563, E 4.7 кОм/47 кОм		E2 • B2 • C1 • E1 • B1 • C2	
34	NSBC124XPDXV6	500	Dnpn/pnp	22 KOM/47 KOM EMT6		E2 • B2 • C1 • E1 • B1 • C2	
34R	μPA812TFB	NEC	npn x2	V_{CB0} = 20 B; I_C = 65 mA; P_D = 200 mB1; I_{D1} = 70150; SC383, I_T > 4.5 $\Gamma\Gamma I_L$		C1 • B2 • C2 • E2 • E1 • B1	
35	NSBC123JPDXV6		Dnpn/pnp	2.2 kOm/4.7 kOm EMT6		E2 • B2 • C1 • E1 • B1 • C2	
35R	μPA812TGB	NEC	npn x2	$V_{CB0} = 20 \text{ B; } I_C = 65 \text{ mA; } P_D = 200 \text{ mBT;}$ SOT3 $h_{21} = 110240; f_T > 4.5 \Gamma \Gamma \mu$ SC88		C1 • B2 • C2 • E2 • E1 • B1	
3Cs	BC857S	INF	pnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 250 mBr; h_{21} = 125630; f_T = 250 MF μ	SC88	E1 • B1 • C2 • E2 • B2 • C1	
3F	µPA873TC	NEC	npn x2	$V_{CB0} = 9 B_i I_C = 100 \text{ mA}; P_D = 230 \text{ mBT}; h_{21} = 100145; f_T > 3 \Gamma \Gamma I_i$	USM-6	C1 • E1 • C2 • E2 • B2 • B1	
3Ft	BC857BS	PHIL	рпр х2	$V_{CB0} = 50 B; I_C = 100 \text{mA}; P_D = 330 \text{mBr}; h_{21} = 220475; f_T > 150 \text{MFu}$	SC88	E1 • B1 • C2 • E2 • B2 • C1	
3G	MGSF3454X	ON	nMOS	I _D = 1.75 A	SOT457, SC74	D•D•G•S•D•D	
14R	µPA811TFB	NEC	npn x2	$V_{DB0} = 20 \text{ B; } I_C = 35 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} = 80160; $ $f_T > 5.5 \Gamma\Gamma \mu$	SOT363, SC88	C1 • B2 • C2 • E2 • E1 • B1	
1591	ZXTD4591E6	ZETEX	npn/pnp	$V_{CB0} = 80 \text{ B}; I_C = 1 \text{ A}; h_{21} > 20; P_D = 1.1 \text{ B}\text{T}$	SOT23-6	C1 • B1 • C2 • E2 • B2 • E1	
45R	μPA811TGB	NEC	npn x2	$V_{CB0} = 20 \text{ B; } I_C = 35 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} = 125250; f_T > 5.5 \Gamma \Gamma_U$	SC88	C1 • B2 • C2 • E2 • E1 • B1	
46	MBT3946DW1	ON	pnp/npn	V_{CB0} = 40 B; I_C = 200 mA; P_D = 150 mBT; h_{21} > 30; f_T > 250 mFu	SC88	E2 • B2 • C1 • E1 • B1 • C2	
4B	μPA891TC	NEC	npn x2	$V_{CB0} = 9 \text{ B, } I_C = 100 \text{ mA; } P_D = 230 \text{ mBT; } h_{21} = 100160; f_T > 3.5 \Gamma \Gamma \mu$	USM-6	C1 • E1 • C2 • B2 • E2 • B1	
C	µPA892TC	NEC	npn x2	V_{CB0} = 15 B; I_C = 35 mA; P_D = 210 mBT; h_{21} = 50100; f_T > 18 $\Gamma\Gamma I_L$		C1 • E1 • C2 • B2 • E2 • B1	
5Ft	BC856S	PHIL	pnp x2	V_{CB0} = 80 B; I_C = 100 мA; P_D = 200 мВт; h_{21} > 110; SC SC f_T > 100 МГц		E1 • B1 • C2 • E2 • B2 • C1	
52s	BAT62-08S	INF	shd x3	C _D < 0.6 nΦ		A1 • A2 • A3 • K3 • K2 • K1	
59s	BAT62-09S	INF	shd x2	C _D < 0.6 пФ SC88		A1 • n.c. • A2 • K2 • n.c. • K1	
iA.	RN4981	TOSH	Dpnp/npn	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; f_T = 200 MFц; R_1/R_2 = 4.7 кOm/4.7 кOm	SC88	E1 • B1 • C2 • E2 • B2 • C1	
ēΑ	RN4981FE	TOSH	Dpnp/npn	$V_{C80} = 50 B; I_C = 100 \text{mA}; P_D = 100 \text{mBT}; f_T = 200 \text{MFu}; R_1/R_2 = 4.7 \text{KOm}/4.7 \text{KOM}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1	

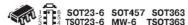




B Rivige Rivig	$L_0 = 100 \text{ MA} \cdot P_0 = 100 \text{ MB} \text{T}, f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 200 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 200 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$	SC88 SOT666 SOT363, SC88 SOT666 SOT363, SC88 SOT666 SOT363, SC88 SOT666	E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1
BR RN4982FE TOSH Donp/npn V ₁₀₉ = 50.8 R ₁ /R ₂ = 10.8 R ₂ /R ₃ = 10.8 R ₃ /R ₃ = 10.8 R ₃ /R ₃ = 22.8 R ₃ /R ₃ = 23.8 R ₃ /R ₃ = 23.8	$L_0 = 100 \text{ MA} \cdot P_0 = 100 \text{ MB} \text{T}, f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 200 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 200 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$ $20 \text{ M} \cdot P_0 = 100 \text{ MB} \cdot f_1 = 200 \text{ MFL}$	SOT363, SC88 SOT666 SOT363, SC88 SOT666 SOT363, SC88 SOT666 SOT363, SC88 SOT666	E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1 E1 •B1 • C2 • E2 •B2 • C1
SC RN4985FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 22 w SD RN4984 TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 22 w SD RN4984FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 47 w SE RN4985 TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 47 w SE RN4985FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 22 w SF RN4986 TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 23 w SF RN4986 TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 508 R ₁ /R ₂ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 4.7 w SF RN4986FE TOSH Donp/npn V ₁₀₉ = 4.7 w SF RN4986 TOSH Donp/npn V	$\Sigma_{\rm h}/22{\rm KOM}$ [$_{\rm b}$ = 100 MB $_{\rm T}$, $f_{\rm f}$ = 200 MG $_{\rm L}$ = 100 MA, $P_{\rm D}$ = 200 MB $_{\rm T}$, $f_{\rm f}$ = 200 MG $_{\rm L}$ = 100 MA, $P_{\rm D}$ = 200 MB $_{\rm T}$, $f_{\rm f}$ = 200 MG $_{\rm L}$ = 100 MA, $P_{\rm D}$ = 100 MB $_{\rm T}$, $f_{\rm f}$ = 200 MG $_{\rm L}$ $_{\rm SM}/47{\rm KoM}$ = 100 MB $_{\rm T}$, $f_{\rm f}$ = 200 MG $_{\rm L}$ $_{\rm CM}/47{\rm KoM}$ = 100 MB $_{\rm T}$, $f_{\rm f}$ = 200 MG $_{\rm L}$ $_{\rm CM}/47{\rm KoM}$ = 100 MB $_{\rm T}$, $f_{\rm f}$ = 200 MG $_{\rm L}$ $_{\rm CM}/47{\rm KoM}$ = 100 MB $_{\rm T}$, $f_{\rm f}$ = 200 MG $_{\rm L}$ $_{\rm CM}/47{\rm KoM}$ $_{\rm CM}$ = 100 MB $_{\rm T}$, $f_{\rm f}$ = 200 MG $_{\rm L}$ $_{\rm CM}/47{\rm KoM}$ $_{\rm CM}$ = 100 MB $_{\rm T}$, $f_{\rm f}$ = 200 MG $_{\rm L}$ $_{\rm CM}/47{\rm KoM}$ $_{\rm F}$ $_{\rm F}$ = 200 MB $_{\rm T}$, $f_{\rm f}$ = 200 MG $_{\rm L}$ $_{\rm F}$	SC88 SOT666 SOT363, SC88 SOT666 SOT363, SC88 SOT666	E1 •B1 • C2 •E2 •B2 • C1 E1 •B1 • C2 •E2 •B2 • C1
Rivi984 TOSH Donp/npn Rivi89, = 22 st	$\Sigma_{\rm h}/22{\rm KDa}$ L ₀ = 100 MA, P ₀ = 200 MBT; $f_{\rm f}$ = 200 MKL, $E_{\rm h}/47{\rm KDa}$ Ma, P ₀ = 100 MBT; $f_{\rm f}$ = 200 MKL, $E_{\rm h}/47{\rm KDa}$ M ₀ = 100 MBT; $f_{\rm f}$ = 200 MKL, $E_{\rm h}/47{\rm KDa}$ M ₀ = 100 MBT; $f_{\rm f}$ = 200 MKL, $E_{\rm f}/47{\rm KDa}$ M ₀ = 100 MBT; $f_{\rm f}$ = 200 MKL, $E_{\rm f}/47{\rm KDa}$ M ₀ = 100 MBT; $f_{\rm f}$ = 200 MKL, $E_{\rm f}/47{\rm KDa}$ M ₀ = 100 MBT; $f_{\rm f}$ = 200 MKL, $E_{\rm f}/47{\rm KDa}$ M ₀ = 100 MBT; $f_{\rm f}$ = 200 MKL, $E_{\rm f}/47{\rm KDa}$ M ₀ = 100 MBT; $f_{\rm f}$ = 200 MKL, $E_{\rm f}/47{\rm KDa}$ M ₀ = 100 MBT; $f_{\rm f}$ = 200 MKL, $E_{\rm f}/47{\rm KDa}$ M ₀ = 100 MBT; $E_{\rm f}/47{\rm MB}$ M ₀ = 100 MBT; $E_{$	SOT363, SC88 SOT666 SOT363, SC88 SOT666 SOT363, SC88	E1 -B1 - C2 - E2 - B2 - C1 E1 -B1 - C2 - E2 - B2 - C1 E1 -B1 - C2 - E2 - B2 - C1 E1 -B1 - C2 - E2 - B2 - C1 E1 -B1 - C2 - E2 - B2 - C1
RN4984FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =47 kg RN4985FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =2 kg RN4985FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =2 kg RN4985FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =2 kg RN4986 TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ /R ₂ =4.7 kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₁ kg RN4986FE TOSH Donp/npn V _{Cop} =50B R ₂	Sin/47 κOis [SC88 SOT666 SOT363, SC88 SOT666 SOT363, SC88	E1+B1+C2+E2+B2+C1 E1+B1+C2+E2+B2+C1 E1+B1+C2+E2+B2+C1 E1+B1+C2+E2+B2+C1
Riving R	$\Sigma_{\rm M}/47$ K/DM $_{\rm C}$ = 100 MA, $P_{\rm D}$ = 200 MBT; $f_{\rm T}$ = 200 MFL; $S_{\rm T}$ = 200 MFL; $S_{\rm T}$ = 100 MA, $P_{\rm D}$ = 100 MBT; $S_{\rm T}$ = 200 MFL; $S_{\rm T}$ = 100 MA, $P_{\rm D}$ = 200 MBT; $S_{\rm T}$ = 200 MFL; $S_{\rm T}$ = 100 MA, $P_{\rm D}$ = 200 MBT; $S_{\rm T}$ = 200 MFL; $S_{\rm T}$ = 200 MFL; $S_{\rm T}$ = 100 MA, $S_{\rm T}$ = 100 MBT; $S_{\rm T}$ = 200 MFL; $S_{\rm T}$ = 100 MBT; $S_{\rm T}$ = 100 M	SOT363, SC88 SOT666 SOT363, SC88	E1 •B1 • C2 •E2 •B2 • C1 E1 •B1 • C2 •E2 •B2 • C1 E1 •B1 • C2 •E2 •B2 • C1
RN4985FE TOSH Dpnp/npn V _{cm} = 50 s R _J /R ₂ = 2 s	OM/47 KOM 10-100 MA PD = 100 MB1; Ft = 200 MFL; 100 MA PD = 100 MB1; Ft = 200 MFL; 100 MA PD = 200 MB1; Ft = 200 MFL; 100 MA PD = 100 MB1; Ft = 200 MFL; 100 MA PD = 100 MB1; Ft = 200 MFL; 100 MA PD = 200 MB1; Ft = 200 MFL;	SC88 SOT666 SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1 E1 • B1 • C2 • E2 • B2 • C1
R ₁ /R ₂ = 2.2 F	.Öm/47 kOm l _o = 100 mA; P _D = 200 mBt; f _t = 200 MFu; ·Om/47 kOm l _o = 100 mA; P _D = 100 mBt; f _t = 200 MFu; ·Om/47 kOm l _o = 100 mA; P _D = 200 mBt; f _t = 200 MFu;	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
R ₁ /R ₂ =4.7 _K F RN4986FE TOSH Donp/non V _{CR0} =50B:	ÖM/47 KOM I _C = 100 MA; P _D = 100 MB⊤; f _T = 200 MF⊔; ÖM/47 KOM I _C = 100 MA; P _D = 200 MB⊤; f _T = 200 MF∪	SC88	9700 ENERGY STEE TO BE EXCENT BASSOCIA
6F RN4986FE TOSH Dpnp/npn V _{CB0} =50 B; R ₁ /R ₂ =4.7 x	:Öm/47 кОм I _C = 100 мА: P _O = 200 мВт: f _T = 200 МГш	SOT666	F1 • B1 • C2 • F2 • B2 • C1
	$I_C = 100 \text{ mA}$: $P_D = 200 \text{ mBT}$: $f_T = 200 \text{ MFu}$:	1	2. 5,-02-22-02-01
6 H RN4987 TOSH Dpnp/npn $V_{080} = 50 B$; $R_{1}/R_{2} = 10 M$	Ом/47 кОм	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
6H RN4987FE TOSH Dpnp/npn V _{CB0} =50 B; R ₁ /R ₂ =10 ki	I _C = 100 мА; P _D = 100 мВт; f _T = 200 МГц; Ом/47 кОм	SOT666	E1 • B1 • C2 • E2 • B2 • C1
6) RN4988 TOSH Dpnp/npn V _{GB0} =50 B; R ₁ /R ₂ =22 ki	$I_{CBD} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; f_T = 200 \text{ MFU}; SOT363, E R_1/R_2 = 22 \text{ KOm}/47 \text{ KOM}$		E1 • B1 • C2 • E2 • B2 • C1
6) RN4988FE TOSH Dpnp/npn V _{CB0} =50B; R ₁ /R ₂ =22 ki	$V_{CBD} = 50 \text{ B}, I_C = 100 \text{ mA}; P_D = 100 \text{ mBT}; f_T = 200 \text{ MFu}; SOT666 IR1/R2 = 22 kOm/47 kOm$		E1 • B1 • C2 • E2 • B2 • C1
6J RN4989 TOSH Dpnp/npn V _{CB0} =50 B; R ₁ /R ₂ =47 kl	I _C = 100 мА; P _D = 200 мВт; f _T = 200 МГц; Ом/22 кОм	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
GJ RN4989FE TOSH Dpnp/npn V _{CB0} =50 B; R ₁ /R ₂ =47 ki	I _C = 100 мА; P _D = 100 мВт; f _T = 200 МГц; Ом/22 кОм	SOT666	E1 • B1 • C2 • E2 • B2 • C1
GK RN4990 TOSH Dpnp/npn V _{CB0} =50 B; R ₁ =4.7 kOw	$I_C = 100 \text{ mA}, P_D = 200 \text{ mB}\text{T}; f_T = 200 \text{ MFu},$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
6K RN4990FE TOSH Dpnp/npn V _{CB0} =50 B; R ₁ =4.7 kOw	$I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu;}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
6M RN4991 TOSH Dpnp/npn V _{CB0} =50 B; R ₁ =10 xO _M	$I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu;}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
6M RN4991FE TOSH Dpnp/npn V _{CB0} =50B; R ₁ =10xOM	$I_C = 100 \text{ mA}, P_D = 100 \text{ mBT}, f_T = 200 \text{ MFU}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
70 μPA801TCFB NEC npn x2 V _{CB0} =20 B; h ₂₁ =7014	I _C =100 мА; Р _D =230 мВт; 0; f _T >3ГГц	USM-6	C1•E1•C2•E2•B2•B1
71 uPA801TCGB NEC non x2 V _{cm} =20 B:	I _C =100 мА; Р _D =230 мВт; !50; f _T > 3 ГГц	USM-6	C1 • E1 • C2 • E2 • B2 • B1
	I _C = 60 мА; P _D = 200 мВт; h ₂₁ = 60120	USM-6	C1 • E1 • C2 • E2 • B2 • B1
h ₂₁ = 1002	$V_{CB0} = 20 \text{ B; } I_C = 60 \text{ mA; } P_D = 200 \text{ mBT;}$ $I_{D1} = 100200; I_T > 3 \Gamma \Gamma I_T$ USM-6		C1 • E1 • C2 • E2 • B2 • B1
73T µPA813TFB NEC npn x2 $V_{CB0} = 20 B$; $f_T = 5.5 \Gamma \Gamma \mu$	V _{con} =20 B; I _c =30 mA; P _n =160 mBr; h _{nt} =60120; SOT36		C1 • B2 • C2 • E2 • E1 • B1
74s BAS70-04S INF shd x4 V _B < 70 B; I _C			A1 • K2 • A3, K4 • A4 • K3 • K1, A2
74T µPA813TGB NEC npn x2 V _{cen} = 20 B;	I _C =30 мА; Р _D =160 мВт; i00; f _T =5.5ГГц	SOT363, SC88	C1 • B2 • C2 • E2 • E1 • B1
	In = 100 mA: Pn = 230 mBT:	USM-6	C1 • E1 • C2 • E2 • B2 • B1
	I _C =100 mA; P _D =200 mBT; h ₂₁ >35;	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
'A	NSBC114EDXV6	ON	Dnpn x2	$V_{C80} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBt; } h_{21} > 35; \\ 10 \text{ kOm}/10 \text{ kOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
В	MUN5212DW1	ON	Dnpn x2	$V_{CB0} = 50 \text{B;} I_C = 100 \text{mA;} P_D = 200 \text{mBt;} h_{21} > 60; \\ 22 \text{KOM} / 22 \text{KOM}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
В	NSBC124EDXV6	ON	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBt; } h_{21} > 60; \\ 22 \text{ kOm}/22 \text{ kOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
C	MUN5213DW1	ON	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBt; } h_{21} > 80; $ $47 \text{ kOm}/47 \text{ kOm}$	SC88	E2 • B2 • C1 • E1 • B1 • C2
'C	NSBC144EDXV6	ON	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBt; } h_{21} > 80; $ $47 \text{ kOm}/47 \text{ kOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
'D	MUN5214DW1	ON	Dnpn x2	10 кОм/47 кОм SC8		E2 • B2 • C1 • E1 • B1 • C2
D O	NSBC114YDXV6	ON	Dnpn x2	10 кОм/47 кОм EMT6		E2 • B2 • C1 • E1 • B1 • C2
Έ	MUN5215DW1	ON	Dnpn x2	R ₁ 10 кОм SC88		E2 • B2 • C1 • E1 • B1 • C2
Έ	NSBC114TDXV6	ON	Dnpn x2	R ₁ 10 kOm EMT6		E2 • B2 • C1 • E1 • B1 • C2
F	MUN5216DW1	ON	Dnpn x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBt}; h_{21} > 160; R_1 4.7 \text{ kOm}$	SC88	E2 • B2 • C1 • E1 • B1 • C2
7F	NSBC143TDXV6	ON	Dnpn x2	R ₁ 4.7 kOm EMT6		E2 • B2 • C1 • E1 • B1 • C2
7G	MUN5230DW1	ON	Dnpn x2	1 KOm/1 KOm SC88		E2 • B2 • C1 • E1 • B1 • C2
7G	NSBC113EDXV6	ON	Dnpn x2	1 KOM/1 KOM EMTE		E2 • B2 • C1 • E1 • B1 • C2
Ή	MUN5231DW1	ON	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBt; h_{21} > 8; SOT363, SC88		E2 • B2 • C1 • E1 • B1 • C2
7H	NSBC123EDXV6	ON	Dnpn x2	$V_{C80} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBr; } h_{21} > 8; $ SOT560 2.2 kOm/2.2 kOm EMT6		E2 • B2 • C1 • E1 • B1 • C2
7J	MUN5232DW1	ON	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBt; h_{21} > 15; 4.7 kOm/4.7 kOm	SC88	E2 • B2 • C1 • E1 • B1 • C2
7J	NSBC143EDXV6	ON	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBr; } h_{21} > 15; \\ 4.7 \text{ kOm}/4.7 \text{ kOm}$	EMT6	E2 • B2 • C1 • E1 • B1 • C2
7K	MUN5233DW1	ON	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBr; } h_{21} > 80; 4.7 \text{ kOm}/47 \text{ kOm}$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
7K	NSBC143ZDXV6	ON	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBr; } h_{21} > 80; \\ 4.7 \text{ kOm}/47 \text{ kOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
7L	MUN5234DW1	ON	Dnpn x2	$V_{DB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBr; } h_{21} > 80; \\ 22 \text{ KOm}/4.7 \text{ KOM}$	SC88	E2 • B2 • C1 • E1 • B1 • C2
7L	NSBC124XDXV6	ON	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBr; } h_{21} > 80; \\ 22 \text{ KOM}/47 \text{ KOM}$	EMT6	E2 • B2 • C1 • E1 • B1 • C2
M	MUN5235DW1	ON	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBt; } h_{21} > 80; \\ 2.2 \text{ kOm}/4.7 \text{ kOm}$	SC88	E2 • B2 • C1 • E1 • B1 • C2
7M	NSBC123JDXV6	ON	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 357 \text{ mBt; } h_{21} > 80; \\ 2.2 \text{ kOm}/4.7 \text{ kOm}$	SOT563, EMT6	E2 • B2 • C1 • E1 • B1 • C2
'N	MUN5236DW1	ON	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBr; } h_{21} > 80; \\ 100 \text{ kOm}/100 \text{ kOm}$	SC88	E2 • B2 • C1 • E1 • B1 • C2
'N	NSBC115EDXV6	ON	Dnpn x2			E2 • B2 • C1 • E1 • B1 • C2
P.	MUN5237DW1	ON	Dnpn x2			E2•B2•C1•E1•B1•C2
7P	NSBC144WDXV6	ON	Dnpn x2	V _{CB0} = 50 B; I _C = 100 mA; P _D = 357 mBt; h ₂₁ > 80; S 47 kOm/22 kOm		E2 • B2 • C1 • E1 • B1 • C2
3s	BAT68-08S	INF	shd x3	V_R < 8 B; I_F < 130 mA; V_F (I_F = 10 mA) < 0.5 B; I_R < 0.1 mKA; C_0 < 1.0 n Φ	SOT363, SC88	A1 • A2 • A3 • K3 • K2 • K1
17	µPA814TC	NEC	npn x2	$V_{CB0} = 9 \text{ B; } I_C = 100 \text{ mA; } P_D = 230 \text{ mBT; } h_{21} = 80160; $ $f_T > 4 \text{ TFu}$	USM-6	C1 • B2 • C2 • E2 • E1 • B1





Код	Типономинал	Б	Ф	Особенности	Корпус			
T88	μ P A814T	NEC	npn x2	$V_{CB0} = 9 B; I_C = 100 \text{ mA}; P_D = 230 \text{ mBT}; h_{21} = 80160; f_7 > 4 \Gamma \Gamma_H$	SOT363, SC88	C1 • B2 • C2 • E2 • E1 • B1		
89s	BAT68-09S	INF	shd x2	V_R < 8 B; I_F < 130 mA; V_F (I_F = 10 mA) < 0.5 B; I_R < 0.1 mKA; C_O < 1.0 n Φ	SOT363, SC88	A1 • n. c. • A2 • K2 • n. c. • K1		
A1s	BAW56S	INF	dix4	$V_R \le 80 \text{ B}; I_F \le 200 \text{ mA}; V_F (I_F = 150 \text{ mA}) \le 1.25 \text{ B}; $ $C_D \le 2.0 \text{ n}\Phi; t_{RR} \le 4 \text{ hc}$	SOT363, SC88	K1 • K2 • A3, A4 • K4 • K3 • A2, A1		
A1s	BAW56U	INF	dix4	V_B < 80 B; I_F < 200 mA; V_F (I_F = 150 mA) < 1.25 B; C_D < 2.0 n Φ ; t_{BB} < 4 H c	SOT457, SC74	K1 • K2 • A3, A4 • K4 • K3 • A2, A1		
A1t	BAW56S	PHIL	dix2	V_R <85 B; I_F <250 mA; V_F (I_F =50 mA)<1 B; I_R <1 m/A; C_D <2.0 n Φ ; I_{RR} <4 HC	SOT363, SC88	K1 • K2 • A3, A4 • K4 • K3 • A2, A1		
A2	MBT3906DW1	ON	pnp x2	$V_{CB0} = 40 \text{ B; } I_C = 200 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} > 30; $ $f_T > 250 \text{ MFц}$	V _{CB0} =40 B; I _C =200 мА; P ₀ =150 мВт; h ₂₁ >30; SC363, E f ₁ >250 МГц SC88			
A40	OPA363I	TI	OA	R-R; V_{DD} = 1.85.5B; f_{BD} = 7 MF $_{U}$; I_S = 1.4 mA; V_{DSI} < 0.9 mB	SOT23-6	OUT • V- • +IN • -IN • ENBL • V+		
A4s	BAV70S	INF	di x4	00		A1 • A2 • K3, K4 • A4 • A3 • K1, K2		
A4s	BAV70U	INF	di x4	11. 11		A1 • A2 • K3, K4 • A4 • A3 • K1, K2		
A5	HN2D02FU	TOSH	di x3			A1 • A2 • A3 • K3 • K2 • K1		
A6	HN2S01F	TOSH	shd x3			K1 • K2 • K3 • A3 • A2 • A1		
A6	HN2S01FU	TOSH	shd x3	$V_R < 10 \text{ B}; I_F < 100 \text{ mA}; V_F (I_F = 100 \text{ mA}) < 0.5 \text{ B}; $ $C_D < 40 \text{ n}\Phi$				
A6s	BAS16S	INF	dix 3	V_R <80 B; I_F <200 mA; V_F (I_F =150 mA)<1.25 B; SOT36: SC88		A1 • A2 • A3 • K3 • K2 • K1		
A6s	BAS16U	INF	dix 3	V _R < 80 B; I _F < 200 мА; V _F (I _F = 150 мА) < 1.25 B; SCT I _R < 50 мкА SCT		A1 • A2 • A3 • K3 • K2 • K1		
A7s	BAV99S	INF	di x4	V_R < 80 B; I_F < 200 mA; V_F (I_F = 150 mA) < 1.25 B; I_R < 0.15 mKA; C_D < 1.5 n Φ ; I_{RR} < 4 Hc	SOT363, SC88	A1 • K2 • A3, K4 • A4 • K3 • A2, K1		
A7s	BAV99U	INF	di x4	V_R < 80 B; I_F < 200 mA; V_F (I_F = 150 mA) < 1.25 B; I_R < 0.15 m/A; C_D < 1.5 n Φ ; I_{RR} < 4 Hc	SOT457, SC74	A1 • K2 • A3, K4 • A4 • K3 • A2, K1		
A8	HN2S03FU	TOSH	shd x3	V_B < 20 B; I_F < 50 mA; V_F (I_F = 50 mA) < 0.55 B; C_D = 3.9 n Φ	SOT363, SC88	K1 • K2 • K3 • A3 • A2 • A1		
A9	HN2S02FU	TOSH	shd x3	$V_R < 40 \text{ B; } I_F < 100 \text{ mA; } V_F (I_F = 100 \text{ mA}) < 0.6 \text{ B; } C_D = 18 \text{ n} \Phi$	SOT363, SC88	K1 • K2 • K3 • A3 • A2 • A1		
A9A	AD8591ART	AD	OA	f _{BD} =2.2 МГц; P _D =7 мВт; V _{DD} =2.56 В	SOT23-6	OUT A • V - • + IN A • - IN A • SD • V+		
AAA	MAX9010EXT	MAX	стр	V _{DSI} < ±7 mB; V _{CC} = 4.55.5 B; I _{CC} < 2.1 mA	SOT363, SC88	OUT • GND • IN+ • IN- • VCC • VCC		
AAAA	MAX2633EUT	MAX	amp	$V_{CC} = 2.75.5 \text{ B; } f_P < 900 \text{ MFu; } I_{CC} = 6.6 \text{ mA}$	SOT23-6	SHDN • GND • OUT • VCC • BIAS • IN		
AAAA	MAX5161LEZT	MAX	Dpot	32 повиции; 50 кОм; V _{DD} =2.75.5 В	SOT23-6	L • H • GND • U/D • INC • VDD		
AAAB	MAX4180EUT	MAX	OA	V _{DD} = +5/±2.25±5.5 B; f _{BD} = 270 MΓц; V _{DSI} < ±7 мВ	SOT23-6	OUT • VEE • IN+ • IN- • SHDN • VCC		
AAAB	MAX5161MEZT	MAX	Dpot	32 повиции; 100 кОм; V _{DO} =2.75.5 В	SOT23-6	L • H • GND • U/D • INC • VDD		
AAAC	MAX4181EUT	MAX	OA			CUT • VEE • IN+ • IN- • SHDN • VCC		
AAAC	MAX5161NEZT	MAX	Dpot	32 повиции; 200 кОм; V _{DO} = 2.75.5 В	SOT23-6	L • H • GND • U/D • INC • VDD		
AAAD	MAX4223EUT	MAX	OA	V _{DD} =±2.85±5.5 B; f _{BD} =1 ГГц; V _{DSI} <7мВ	SOT23-6	CUT • VEE • IN+ • IN- • SHDN • VCC		
AAAE	MAX4224EUT	MAX	OA	V _{DD} = ±2.85±5.5 В; f _{BD} = 1 ГГц; V _{DSI} < 7мВ	SOT23-6	CUT • VEE • IN+ • IN- • SHDN • VCC		
AAAF	MAX2660EUT	MAX	upmixer	V _{CC} =2.75.5 B; f _P =4002500 МГц; I _{CC} =4.8 мА	SOT23-6	LO • GND • IFIN • RFOUT • VCC • SHDN		
AAAG	MAX2661EUT	MAX	upmixer	V _{CC} =2.75.5 B; f _P =4002500 МГц; I _{CC} =8.3 мА		LO • GND • IFIN • RFOUT • VCC • SHDN		
AAAH	MAX2662EUT	MAX	upmixer	V _{CC} = 2.75.5 B; f _p = 4002500 MF _L	SOT23-6	LOIN • GND • IFIN • RFOUT • VCC • SHDN		



Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
AAAI	MAX5383EZT	MAX	DAC	8-pasp.; SPI/QSPI/Microwire; V _{DO} = 2.73.6 B; V _{REF} = 2 B	TSOT23- 6	OUT • GND • VDD • DIN • SCLK • CS
AAAJ	MAX2671EUT	MAX	upmixer	V _{CC} = 2.75.5 B; f _P = 4002500 МГц; I _{CC} = 11.8 мА	SOT23-6	LO • GND • IFIN • RFOUT • VCC • SHDN
AAAJ	MAX5385EZT	MAX	DAC	8-pasp.; SPI/QSPI/Microwire; V _{DO} = 2.75.5 B; V _{REF} = 0.9 x V _{DD}	TSOT23- 6	OUT • GND • VDD • DIN • SCLK • CS
AAAL	MAX2663EUT	MAX	upmixer	V _{CC} = 2.75.5 B; f _P = 4002500 МГц; I _{CC} = 3.0 мА	SOT23-6	LO • GND • IFIN • RFOUT • VCC • SHDN
AAAM	MAX4544EUT	MAX	asw	SPDT; R _{ON} < 75 Om; V _{DD} = 2.712 B	SOT23-6	IN •V+•GND•NC•COM•NO
AAAO	MAX998EUT	MAX	стр	R-R; V _{DSI} < ±3 mB; V _{CC} = 2.75.5 B; I _{CC} < 650 mKA	SOT23-6	OUT • GND • IN+ • IN- • SHDN • VCC
AAAQ	MAX4529UT	MAX	asw	двунапр. РЧ/видео; R _{DN} < 1000м; V _{DO} = 2.712/±2.7±6 B	SOT23-6	NC • V+ • V- • IN • GND • COM
AAAR	MAX2680EUT	MAX	dnmixer	50		LO • GND • RFIN • IFOUT • VCC • SHDN
AAAS	MAX2681EUT	MAX	dnmixer			LO • GND • RFIN • IFOUT • VCC • SHDN
AAAT	MAX2682EUT	MAX	dnmixer	V _{CC} =2.75.5 B; f _P =4002500 МГц; I _{CC} < 21.8 мА	SOT23-6	LO • GND • RFIN • IFOUT • VCC • SHDN
AAAU	MAX6817EUT	MAX	swd x2	V _{CC} =2.75.5 B; I _{CC} < 20 mkA	SOT23-6	IN1 • GND • IN2 • OUT2 • VCC • OUT1
AAAV	MAX2640EUT	MAX	amp	SiGe; V_{CC} = 2.75.5B; f_p = 4001500 MFu; I_{CC} = 3.5 mA	SOT23-6	RFIN • GND • GND • RFOUT • GND • VCC
AAAW	MAX2641EUT	MAX	amp	SiGe; V _{CC} = 2.75.5 B; f _P = 14002500 ΜΓц; I _{CC} = 3.5 мA	SOT23-6	RFIN • GND • GND • RFOUT • GND • VCC
AAAX	MAX2470EUT	MAX	amp	$V_{CC} = 2.75.5 \text{ B}; f_p = 10200/10500 MFu;$ SOT: $I_{CC} < 7.4 \text{ MA}$		OUT • GND • OUT • HI/LO (IN) • IN • VCC
AAAY	MAX2471EUT	MAX	amp	V _{CC} = 2.75.5 B; f _P = 10500МГц; I _{CC} < 7.4мА SOT		OUT • GND • OUT • HI/LO (IN) • IN • VCC
AAAZ	MAX2472EUT	MAX	amp	V _{CC} = 2.75.5 B; f _P = 5002500 МГц; I _{CC} < 8 мА	SOT23-6	OUT1 • GND • OUT2 • IN • GND • VCC
AAB	MAX4401AXT	MAX	OA	R-R; V_{00} = 2.55.5 B; f_{80} = 800 kFu; V_{0S} < 5.5 mB	SOT363, SC88	IN+ • VSS • IN- • OUT • SHDN • VDD
AABA	MAX2473EUT	MAX	amp	$V_{CC} = 2.75.5 B; f_P = 5002500 MFi; I_{CC} = 2.7 mA$	SOT23-6	OUT • GND • BIAS • IN • GND • VCC
AABB	MAX2605EUT	MAX	VCO	V _{CC} = 2.75.5 B; f _P = 4570 MFu; I _{CC} = 1.9 mA	SOT23-6	IND • GND • TUNE • CUT- • VCC • CUT+
AABC	MAX2606EUT	MAX	VCO	V _{CC} = 2.75.5 B; f _P = 70150МГц; I _{CC} = 2.1 мА	SOT23-6	IND • GND • TUNE • OUT- • VCC • OUT+
AABD	MAX2607EUT	MAX	VCO	V _{CC} = 2.75.5 B; f _P = 150300 MΓц; I _{CC} = 2.1 мA	SOT23-6	IND • GND • TUNE • OUT- • VCC • OUT+
AABE	MAX2608EUT	MAX	VCO	V _{CC} = 2.75.5 B; f _P =300500 MΓц; I _{CC} = 2.7 мA	SOT23-6	IND • GND • TUNE • CUT- • VCC • OUT+
AABF	MAX2609EUT	MAX	VCO	V _{CC} =2.75.5 B; f _P =500650 МГц; I _{CC} =3.6 мА	SOT23-6	IND • GND • TUNE • OUT- • VCC • OUT+
AABG	MAX6575LZUT	MAX	dts	T _{AMB} = -40125 °C; V _{CC} = 2.75.5 B; I _{CC} < 400 mA	SOT23-6	VDD • GND • n. c. • TS0 • TS1 • I/O
AABH	MAX6575HZUT	MAX	dts	T _{AMB} = -40125 'C; V _{CC} = 2.75.5 B; I _{CC} < 400 mA	SOT23-6	VDD • GND • n. c. • TS0 • TS1 • I/O
AABI	MAX6576ZUT	MAX	dts	T _{AMB} = -40125 °C; V _{CC} = 2.75.5 B; I _{CC} < 400 mA		VDD • GND • n. c. • TS0 • TS1 • OUT
AABJ	MAX6577ZUT	MAX	dts	T _{AMB} = -40125 °C; V _{CC} = 2.75.5 B; I _{CC} < 400 mA	SOT23-6	VDD • GND • n. c. • TS0 • TS1 • OUT
AABN	MAX4173TEUT	MAX	CSA	V _{DD} = 328 B; f _{BD} = 1.7 МГц; Gain = 20; I _{CC} < 1 мА	SOT23-6	GND • GND • VCC • RS+ • RS- • OUT
AABO	MAX4173FEUT	MAX	CSA	V _{DD} = 328 B; f _{BD} = 1.7 МГц; Gain = 50; I _{CC} < 1 мА	SOT23-6	GND • GND • VCC • RS+ • RS- • OUT
AABP	MAX4173HEUT	MAX	CSA	$V_{DD} = 328 \text{ B; } f_{BD} = 1.7 \text{ MFu; Gain} = 100; I_{CC} < 1 \text{ MA}$	SOT23-6	GND • GND • VCC • RS+ • RS- • OUT
AABQ	MAX4285EUT	MAX	buf	V_{DO} = +2.85+6.5/±1.425±3.25 B; f_{BO} = 250 MFu; V_{DS} < ±12 MB		OUT • VEE • IN+ • IN- • DISABLE • VCC
AABR	MAX4286EUT	MAX	buf	V_{DO} = +2.85+6.5/±1.425±3.25 B; f_{BO} = 150 MFu; V_{DS} < ±12 MB	SOT23-6	OUT • VEE • IN+ • IN- • DISABLE • VCC
AABV	MAX1697REUT	MAX	vcpcon	V _{IN} = 1.255.5 В; f _P = 12 кГц; I _{DUT} = 60 мА	SOT23-6	OUT • IN • C1- • GND • SHDN • C1+
AABW	MAX1697SEUT	MAX	vepcon	V _{IN} = 1.255.5 B; f _P = 35 кГц; I _{OUT} = 60 мА	SOT23-6	OUT • IN • C1- • GND • SHDN • C1+





Код	Типономинал	Б	ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
AABX	MAX1697TEUT	MAX	vepcon	V _{IN} = 1.255.5 B; f _P = 125 κΓυ; I _{CHT} = 60 мA	SOT23-6	OUT • IN • C1- • GND • SHDN • C1+
AABY	MAX1697UEUT	MAX	vepcon	V _{IN} = 1.255.5 B; f _P = 250 κΓιμ I _{CHT} = 60 мA	SOT23-6	OUT • IN • C1- • GND • SHDN • C1+
AABZ	MAX4510EUT	MAX	asw	SPST; R _{DN} < 225 OM; V _{DD} = 936/±4.5±20B		V+•V-•IN•GND•COM•NC
AAC	MAX2642EXT	MAX	amp	SiGe; V _{CC} =2.75.5 B; f _p =8001000 MFu; I _{CC} <7.5 MA	SOT363, SC88	BIAS • GND • RFIN • VCC • GND • RFOUT
AACB	MAX6351LSUT	MAX	mrc	$V_{TR1} = 4.63B$; $V_{TR2} = 2.93B$; $V_{DD} = 1.25.5B$; $I_{CC} \le 50 \text{ MKA}$	SOT23-6	RST1 • GND • MR • VCC2 • RST2 • VCC1
AACC	MAX6351SYUT	MAX	mrc	$V_{TR1} = 2.93B$; $V_{TR2} = 2.19B$; $V_{DD} = 1.25.5B$; $I_{CC} < 50 \text{ MKA}$	SOT23-6	RST1 • GND • MR • VCC2 • RST2 • VCC1
AACD	MAX6355LSUT	MAX	mrc	$V_{TR1} = 4.63B$; $V_{TR2} = 2.93B$; $V_{DD} = 1.25.5B$; $I_{CC} \le 50 \text{ m/kA}$	SOT23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AACE	MAX6355SYUT	MAX	mrc	$V_{TR1} = 2.93B$; $V_{TR2} = 2.19B$; $V_{D0} = 1.25.5B$; $I_{CC} \le 50 \text{ MKA}$	SOT23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AACF	MAX6356LSUT	MAX	mrc	$V_{TR1} = 4.63 B$; $V_{TR2} = 2.93 B$; $V_{D0} = 1.25.5 B$; $I_{CC} \le 50 \text{ MKA}$	SOT23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AACG	MAX6356SYUT	MAX	mrc	V_{TRT} = 2.93 B; V_{TR2} = 2.19 B; V_{DD} = 1.25.5 B; I_{CC} < 50 MKA	SOT23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AACH	MAX6357LSUT	MAX	mrc	V_{TRT} = 4.63 B; V_{TR2} = 2.93 B; V_{D0} = 1.25.5 B; I_{CC} < 50 MKA	SOT23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AACI	MAX6357SYUT	MAX	mrc	$V_{TRT} = 2.93B$; $V_{TR2} = 2.19B$; $V_{DO} = 1.25.5B$; $I_{CC} \le 50 \text{ MKA}$	SOT23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AACJ	MAX6358LSUT	MAX	mrc	$V_{TRT} = 4.63 \text{B}; V_{TR2} = 2.93 \text{B}; V_{D0} = 1.25.5 \text{B}; V_{CC} \le 50 \text{mkA}$	SOT23-6	RST • GND • MR • VCC2 • WDI • VCC1
AACK	MAX6358SYUT	MAX	mrc	$V_{TR1} = 2.93B$; $V_{TR2} = 2.19B$; $V_{DO} = 1.25.5B$; $I_{CC} \le 50$ m/kA	SOT23-6	RST • GND • MR • VCC2 • WDI • VCC1
AACL	MAX6359LSUT	MAX	mrc	$V_{TRT} = 4.63 B$; $V_{TR2} = 2.93 B$; $V_{D0} = 1.25.5 B$; $I_{CC} \le 50 \text{ m/kA}$	SOT23-6	RST • GND • MR • VCC2 • WDI • VCC1
AACM	MAX6359SYUT	MAX	mrc	$V_{TRT} = 2.93B$; $V_{TR2} = 2.19B$; $V_{DO} = 1.25.5B$; $I_{CC} \le 50 \text{ MKA}$	SOT23-6	RST • GND • MR • VCC2 • WDI • VCC1
AACN	MAX6360LSUT	MAX	mrc	$V_{TRT} = 4.63 B$; $V_{TR2} = 2.93 B$; $V_{DO} = 1.25.5 B$; $I_{CC} \le 50 \text{ m/kA}$	SOT23-6	RST • GND • MR • VCC2 • WDI • VCC1
AACO	MAX6360SYUT	MAX	mrc	$V_{TR1} = 2.93B$; $V_{TR2} = 2.19B$; $V_{D0} = 1.25.5B$; $I_{CC} \le 50$ m/kA	SOT23-6	RST • GND • MR • VCC2 • WDI • VCC1
AACP	MAX6342LUT	MAX	mrc	$V_{TR} = 4.63 \text{ B}; V_{DD} = 1.25.5 \text{ B}; I_{CC} < 60 \text{ mKA}$	SOT23-6	VCC • GND • PFI • PFO • MR • RES
AACQ	MAX6342MUT	MAX	mrc	$V_{TR} = 4.38 \text{ B}; V_{DD} = 1.25.5 \text{ B}; I_{CC} < 60 \text{ mKA}$	SOT23-6	VCC • GND • PFI • PFO • MR • RES
AACR	MAX6342TUT	MAX	mrc	$V_{TR} = 3.08 \text{ B}; V_{DD} = 1.25.5 \text{ B}; I_{CC} < 60 \text{ mKA}$	SOT23-6	VCC • GND • PFI • PFO • MR • RES
AACS	MAX6342SUT	MAX	mrc	V _{TR} =2.93 B; V _{DD} =1.25.5 B; I _{CC} < 60 мкA	SOT23-6	VCC • GND • PFI • PFO • MR • RES
AACT	MAX6342RUT	MAX	mrc	V _{TR} =2.63 B; V _{DD} =1.25.5 B; I _{CC} < 60 мкА	SOT23-6	VCC • GND • PFI • PFO • MR • RES
AACU	MAX6342ZUT	MAX	mrc	V _{TB} =2.33 B; V _{DD} =1.25.5 B; I _{CC} < 60 мкА	SOT23-6	VCC • GND • PFI • PFO • MR • RES
AACV	MAX6343LUT	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} < 60 мкА	SOT23-6	VCC • GND • PFI • PFO • MR • RES
AACW	MAX6343MUT	MAX	mrc	V _{тв} =4.38 B; V _{DD} =1.25.5 B; I _{CC} < 60 мкА	SOT23-6	VCC • GND • PFI • PFO • MR • RES
AACX	MAX6343TUT	MAX	mrc	V _{тв} =3.08 B; V _{DD} =1.25.5 B; I _{CC} < 60 мкА	SOT23-6	VCC • GND • PFI • PFO • MR • RES
AACY	MAX6343SUT	MAX	mrc	V _{TB} = 2.93 B; V _{DD} = 1.25.5 B; I _{DD} < 60 MKA	SOT23-6	VCC • GND • PFI • PFO • MR • RES
AACZ	MAX6343RUT	MAX	mrc	V _{тв} = 2.63 B; V _{DD} = 1.25.5 B; I _{CC} < 60 мкА	SOT23-6	VCC • GND • PFI • PFO • MR • RES
AAD	MAX2643EXT	MAX	amp	SiGe; V _{CC} =2.75.5 B; f _P =8001000 MFu; I _{CC} <7.5 MA	SOT363, SC88	BIAS • GND • RFIN • VCC • GND • RFOUT
AADA	MAX6343ZUT	MAX	mrc	V _{TB} = 2.33 B; V _{DD} = 1.25.5 B; I _{CC} < 60 мкА	SOT23-6	VCC • GND • PFI • PFO • MR • RES
	MAX9011EUT	MAX	cmp	V _{DSI} < ±7 MB; V _{CC} = 4.55.5 B; I _{CC} < 2.1 MA		CUT • GND • IN+ • IN- • LE • VCC
	MAX5363EUT	MAX	DAC	6-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.73.6B; V _{REE} = 2B	0.00,000,00	OUT • GND • VDD • DIN • SCLK • CS
AADF	MAX5383EUT	MAX	DAC	8-pasp.; SPI/QSPI/Microwire; V _{DD} =2.73.6B; V _{REF} =2B	SOT23-6	OUT • GND • VDD • DIN • SCLK • CS
AADG	MAX5364EUT	MAX	DAC	6-pasp.; SPI/QSPI/Microwire, V _{DD} =4.55.5B; V _{REF} =4B	SOT23-6	OUT • GND • VDD • DIN • SCLK • CS
AADH	MAX5384EUT	MAX	DAC	8-pasp.; SPI/QSPI/Microwire; V _{DD} = 4.55.5B; V _{REF} = 4B	SOT23-6	OUT • GND • VDD • DIN • SCLK • CS





Код	Типономинал	БФ		Особенности	Корпус	Ц: 1•2•3•4•5•6	
AADI	MAX5365EUT	MAX	DAC	6-pasp.; SPI/QSPI/Microwire; V _{DO} = 2.75.5 B; V _{REF} = 0.9 x V _{DD}	SOT23-6	OUT • GND • VDD • DIN • SCLK • CS	
AADJ	MAX5384EZT	MAX	DAC	8-pasp.; SPI/QSPI/Microwire; V ₀₀ = 4.55.5 B; V _{REF} = 4 B	TSOT23-	OUT • GND • VDD • DIN • SCLK • CS	
AAD J	MAX5385EUT	MAX	DAC	8-pasp.; SPI/QSPI/Microwire; V _{DO} = 2.75.5 B; V _{REF} = 0.9 x V _{DD}	SOT23-6	OUT • GND • VDD • DIN • SCLK • CS	
AADK	MAX4520EUT	MAX	asw	SPST; R _{DN} < 225 O _M ; V _{DD} = 936/±4.5±20 B	SOT23-6	V+•V-•IN•GND•COM•NO	
AADN	MAX4628EUT	MAX	asw	SPST; R _{DN} < 12 Om; V _{DO} = 1.85.5 B	SOT23-6	COM • NO • GND • IN • IN • V+	
AADQ	MAX6344LUT	MAX	mrc	V _{TB} = 4.63 B; V _{DD} = 1.25.5 B; I _{CC} < 60 мкА	SOT23-6	VCC • GND • PFI • PFO • MR • RES	
AADR	MAX6344MUT	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25.5 B; I _{CC} <60 mKA	SOT23-6	VCC • GND • PFI • PFO • MR • RES	
AADS	MAX6344TUT	MAX	mrc	V _{TR} = 3.08 B; V _{DD} = 1.25.5 B; I _{CC} < 60 mKA	SOT23-6	VCC • GND • PFI • PFO • MR • RES	
AADT	MAX6344SUT	MAX	mrc	V _{TR} =2.93 B; V _{DD} =1.25.5 B; I _{CC} <60 mKA	SOT23-6	VCC • GND • PFI • PFO • MR • RES	
AADU	MAX6344RUT	MAX	mrc	V _{TR} = 2.63 B; V _{DD} = 1.25.5 B; I _{CC} < 60 mKA	SOT23-6	VCC • GND • PFI • PFO • MR • RES	
AADV	MAX6344ZUT	MAX	mrc	V _{TR} = 2.33 B; V _{DD} = 1.25.5 B; I _{CC} < 60 мкА	SOT23-6	VCC • GND • PFI • PFO • MR • RES	
4ADW	MAX6345LUT	MAX	mrc	V _{TR} = 4.63 B; V _{DD} = 1.25.5 B; I _{CC} < 60 mKA	SOT23-6	VCC • GND • PFI • PFO • MR • RES	
AADX	MAX6345MUT	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25.5 B; I _{CC} <60 мкA	SOT23-6	VCC • GND • PFI • PFO • MR • RES	
AADY	MAX6345TUT	MAX	mrc	V _{TR} =3.08 B; V _{DD} =1.25.5 B; I _{CC} <60 мкA	SOT23-6	VCC • GND • PFI • PFO • MR • RES	
AADZ	MAX6345SUT	MAX	mrc	V _{TB} =2.93 B; V _{DD} =1.25.5 B; I _{CC} <60 мкА	SOT23-6	VCC • GND • PFI • PFO • MR • RES	
AAEA	MAX6345RUT	MAX	mrc	V _{TB} = 2.63 B; V _{DD} = 1.25.5 B; I _{CC} < 60 mKA	SOT23-6	VCC • GND • PFI • PFO • MR • RES	
AAEB	MAX6345ZUT	MAX	mrc	V _{TB} =2.33 B; V _{DD} =1.25.5 B; I _{CC} <60 мкА	SOT23-6	VCC • GND • PFI • PFO • MR • RES	
AAEC	MAX4323EUT	MAX	OA	R-R; V _{DD} = 2.46.5/±1.2±3.25 В; f _{BD} = 5 МГц; V _{DS} < 3.5 мВ	SOT23-6	OUT • VEE • IN+ • IN- • SHDN • VCC	
\AED	MAX6361LUT46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} <50 мкА	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AEE	MAX6361LUT44	MAX	mrc	V _{TB} = 4.38 B; V _{DD} = 1.25.5 B; I _{CC} < 50 мкА	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
VAEF.	MAX6361LUT31	MAX	mrc	V _{TB} = 3.08 B; V _{DD} = 1.25.5 B; I _{CC} < 50 мкА	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AAEG	MAX6361LUT29	MAX	mrc	V _{TB} = 2.93 B; V _{DD} = 1.25.5 B; I _{DD} < 50 мкА	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
4AEH	MAX6361LUT26	MAX	mrc	V _{TB} = 2.63 B; V _{DD} = 1.25.5 B; I _{CC} < 50 мкА	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AAEI	MAX6361LUT23	MAX	mrc	V _{TR} =2.32 B; V _{DD} =1.25.5 B; I _{CC} <50 mKA	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
4AEJ	MAX6361PUT46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} <50 mKA	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AAEK	MAX6361PUT44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25.5 B; I _{CC} <50 mKA	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AAEL	MAX6361PUT31	MAX	mrc	V _{TB} = 3.08 B; V _{DD} = 1.25.5 B; I _{DC} < 50 mKA	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AAEM	MAX6361PUT29	MAX	mrc	V _{TR} = 2.93 B; V _{DD} = 1.25.5 B; I _{CC} < 50 mKA	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AAEN	MAX6361PUT26	MAX	mrc	V _{TB} = 2.63 B; V _{DD} = 1.25.5 B; I _{CC} < 50 мкА	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AAEO	MAX6361PUT23	MAX	mrc	V _{TR} = 2.32 B; V _{DD} = 1.25.5 B; I _{CC} < 50 mKA	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AAEP	MAX6361HUT46	MAX	mrc	V _{TB} = 4.63 B; V _{DD} = 1.25.5 B; I _{CC} < 50 мкА	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AAEQ	MAX6361HUT44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25.5 B; I _{CC} <50 mKA	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AAER	MAX6361HUT31	MAX	mrc	V _{TR} = 3.08 B; V _{DD} = 1.25.5 B; I _{CC} < 50 mKA	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AAES	MAX6361HUT29	MAX	mrc	V _{TR} = 2.93 B; V _{DD} = 1.25.5 B; I _{CC} < 50 мкА	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AAET	MAX6361HUT26	MAX	mrc	V _{TR} = 2.63 B; V _{DD} = 1.25.5 B; I _{CC} < 50 мкА	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AAEU	MAX6361HUT23	MAX	mrc	V _{TR} = 2.32 B; V _{DD} = 1.25.5 B; I _{CC} < 50 мкА	SOT23-6	RES • GND • MR • VCC • OUT • BAT	
AEV	MAX6362LUT46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} <50 мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT	
AEW	MAX6362LUT44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25.5 B; I _{CC} <50 mKA	SOT23-6	RES • GND • WDI • VCC • OUT • BATT	
AAEX	MAX6362LUT31	MAX	mrc	V _{TR} =3.08 B; V _{DD} =1.25.5 B; I _{CC} <50 mKA	SOT23-6	RES • GND • WDI • VCC • OUT • BATT	
AAEY	MAX6362LUT29	MAX	mrc	V _{TR} =2.93 B; V _{DD} =1.25.5 B; I _{CC} <50 мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT	
AAEZ	MAX6362LUT26	MAX	mrc	V _{TR} = 2.63 B; V _{DO} = 1.25.5 B; I _{CC} < 50 mKA	SOT23-6	RES • GND • WDI • VCC • OUT • BATT	
AAF	MAX4599EXT	MAX	asw	SPDT; R _{ON} < 65 Om; V _{DD} = 2.05.5B	SOT363, SC88	IN •V+•GND•NC•COM•NO	





Код	Типономинал	6	Ф	Особе	нности	Корпус	Ц: 1•2•3•4•5•6
AFA	MAX6362LUT23	MAX	mrc	V _{TR} =2.32B;V _{DD} =1.25	.5В; I _{CC} < 50мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT
AFB	MAX6362PUT46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT
AFC	MAX6362PUT44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT
AAFD	MAX6362PUT31	MAX	mrc	V _{TR} =3.08 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT
AAFE	MAX6362PUT29	MAX	mrc	V _{TR} =2.63 B; V _{DD} =1.25	.5 В; I _{СС} < 50 мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT
AFF	MAX6362PUT26	MAX	mrc	V _{TR} =2.32B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT
AAFG	MAX6362PUT23	MAX	mrc	V _{TR} =2.25 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT
AAFH	MAX6362HUT46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT
AAFI	MAX6362HUT44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT
AAFJ	MAX6362HUT31	MAX	mrc	V _{TR} =3.08 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT
AAFK	MAX6362HUT29	MAX	mrc	V _{TR} =2.93 B; V ₀₀ =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT
AAFL	MAX6362HUT26	MAX	mrc	V _{TR} =2.63 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT
AAFM	MAX6362HUT23	MAX	mrc	V _{TR} =2.32B; V ₀₀ =1.25	.5 В; I _{СС} < 50 мкА	SOT23-6	RES • GND • WDI • VCC • OUT • BATT
AAFN	MAX6363LUT46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25	.5В; I _{CC} < 50мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAFO	MAX6363LUT44	MAX	mrc	V _{TR} =4.38 B; V ₀₀ =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAFP	MAX6363LUT31	MAX	mrc	V _{TR} =3.08 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAFQ	MAX6363LUT29	MAX	mrc	V _{TR} =2.93 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAFR	MAX6363LUT26	MAX	mrc	V _{TR} =2.63 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAFS	MAX6363LUT23	MAX	mrc	V _{TR} =2.32 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAFT	MAX6363PUT46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25	.5В; I _{СС} < 50 мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAFU	MAX6363PUT44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAFV	MAX6363PUT31	MAX	mrc	V _{TR} =3.08 B; V _{DD} =1.25	.5 В; I _{СС} < 50 мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAFW	MAX6363PUT29	MAX	mrc	V _{TR} =2.93 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAFX	MAX6363PUT26	MAX	mrc	V _{TR} =2.63 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAFY	MAX6363PUT23	MAX	mrc	V _{TR} =2.32 B; V _{DD} =1.25	.5 B; I _{CC} < 50 mkA	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAFZ	MAX6363HUT46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAG	MAX2644EXT	MAX	amp	SiGe; V _{CC} =2.75.5B; f _P I _{CC} <11 mA	= 24002500 M Fu;	SOT363, SC88	BIAS • GND • RFIN • VCC • GND • RFOUT
AAGA	MAX6363HUT44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • BATT ON • VCC • CUT • BATT
AAGB	MAX6363HUT31	MAX	mrc	V _{TR} =3.08 B; V _{DD} =1.25	.5 В; I _{CC} < 50 мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
AAGC	MAX6363HUT29	MAX	mrc	V _{TR} = 2.93 B; V _{DD} = 1.25.5 B; I _{CC} < 50 мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAGD	MAX6363HUT26	MAX	mrc	$V_{TR} = 2.63 \text{ B; } V_{D0} = 1.25.5 \text{ B; } I_{CC} < 50 \text{ mKA}$	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAGE	MAX6363HUT23	MAX	mrc	V _{TR} =2.32 B; V _{DO} =1.25.5 B; I _{CC} <50 мкА	SOT23-6	RES • GND • BATT ON • VCC • OUT • BATT
AAGF	MAX6364LUT46	MAX	mrc	$V_{TR} = 4.63 \text{ B; } V_{DO} = 1.25.5 \text{ B; } I_{CC} < 50 \text{ mKA}$	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGG	MAX6364LUT44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25.5 B; I _{CC} <50 mKA SOT23-6		RES • GND • RES IN • VCC • OUT • BATT
AAGH	MAX6364LUT31	MAX	mrc	$V_{TR} = 3.08 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 50 \text{ mKA}$	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGI	MAX6364LUT29	MAX	mrc	V _{TR} =2.93 B; V ₀₀ =1.25.5 B; I _{CC} <50 мкА	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGJ	MAX6364LUT26	MAX	mrc	$V_{TR} = 2.63 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 50 \text{ mKA}$	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGK	MAX6364LUT23	MAX	mrc	V _{TR} =2.32 B; V _{DO} =1.25.5 B; I _{CC} <50 мкА	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGL	MAX6364PUT46	MAX	mrc	V _{TR} =4.63 B; V _{DO} =1.25.5 B; I _{CC} <50 мкА	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGM	MAX6364PUT44	MAX	mrc	V_{TR} = 4.38 B; V_{D0} = 1.25.5 B; I_{CC} < 50 mKA	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGN	MAX6364PUT31	MAX	mrc	V _{TR} = 3.08 B; V _{DD} = 1.25.5 B; I _{CC} < 50 мкА	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGO	MAX6364PUT29	MAX	mrc	$V_{TR} = 2.93 \text{ B; } V_{DD} = 1.25.5 \text{ B; } I_{CC} < 50 \text{ mKA}$	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGP	MAX6364PUT26	MAX	mrc	V _{TR} =2.63 B; V _{DD} =1.25.5 B; I _{CC} <50 мкА	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGQ	MAX6364PUT23	MAX	mrc	$V_{TR} = 2.32 \text{ B; } V_{DD} = 1.25.5 \text{ B; } I_{CC} < 50 \text{ mKA}$	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGR	MAX6364HUT46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} < 50 мкА	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGS	MAX6364HUT44	MAX	mrc	$V_{TR} = 4.38 \text{ B; } V_{DD} = 1.25.5 \text{ B; } I_{CC} < 50 \text{ mKA}$	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGT	MAX6364HUT31	MAX	mrc	V _{TR} = 3.08 B; V _{DD} = 1.25.5 B; I _{CC} < 50 мкА	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGU	MAX6364HUT29	MAX	mrc	V _{TR} =2.93 B; V _{DD} =1.25.5 B; I _{CC} <50 mKA	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGV	MAX6364HUT26	MAX	mrc	V _{TR} =2.63 B; V _{DD} =1.25.5 B; I _{CC} < 50 мкА	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
AAGW	MAX6364HUT23	MAX	mrc	$V_{TR} = 2.32 \text{ B; } V_{DO} = 1.25.5 \text{ B; } I_{CC} < 50 \text{ mKA}$	SOT23-6	RES • GND • RES IN • VCC • OUT • BATT
ДАН	MAX9030AXT	MAX	стр	R-R; V _{DSI} <±5 mB; V _{DD} =2.55.5 B; I _{DD} <55 mkA	SOT363, SC88	IN+ • VSS • IN- • OUT • SHDN • VDD
AAHA	MAX6510CAUT	MAX	tempsw	V _{CC} =2.75.5 B; T _{TH} =-40+125°C; I _{CC} <165 mkA	SOT23-6	SET • GND • OUT, OUT • HYST • OUTSET • VCC
AAHB	MAX6510HAUT	MAX	tempsw	V _{CC} =2.75.5 B; T _{TH} =-40+125°C; I _{CC} <165 mkA	SOT23-6	SET • GND • OUT, OUT • HYST • OUTSET • VCC
AAHC	MAX4599EUT	MAX	asw	SPDT; R _{CN} < 65 OM; V _{DD} = 2.05.5B	SOT23-6	IN •V+•GND•NC•COM•NO
AAHF	MAX9041AEUT	MAX	cmp+vref	R-R; V _{DSI} <±7 _M B; V _{CC} =2.55.5B; V _{REF} =2.048B; I _{CC} <72 _M KA	SOT23-6	OUT • VEE • IN+ • IN- • REF • VCC
AAHG	MAX9051AEUT	MAX	cmp + vref	R-R; V _{DSI} <±7 _M B; V _{CC} =2.75.5B; V _{REF} =2.500B; I _{CC} <72 _M KA	SOT23-6	OUT • VEE • IN+ • IN- • REF • VCC
AAHH	MAX9041BEUT	MAX	cmp + vref	R-R; V_{DSI} < ±7mB; V_{CC} =2.55.5B; V_{REF} =2.048B; I_{CC} <72mkA	SOT23-6	OUT • VEE • IN+ • IN- • REF • VCC
AAHI	MAX9051BEUT	MAX	cmp+vref	R-R; V _{DSI} <±7 _M B; V _{CC} =2.75.5 B; V _{REF} =2.500 B; I _{CC} <72 _{MK} A	SOT23-6	OUT • VEE • IN+ • IN- • REF • VCC





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
AAHJ	MAX3188EUT	MAX	trnsmit	RS-232; V _{CC} = ±4.5±6 B; f _{DR} = 256 Кбит/с; I _{CC} < 170 мкА	SOT23-6	SHDN • GND • TIN • TOUT • VEE • VCC
AAHK	MAX3189EUT	MAX	tmsmit	RS-232; V_{CC} = $\pm 4.5\pm 6$ B; f_{DR} = 1 MG/IT/C; I_{CC} < 170 MKA	SOT23-6	SHDN • GND • TIN • TOUT • VEE • VCC
AAHL	MAX4645EUT	MAX	asw	SPST; R _{ON} < 30M; V _{DD} = 1.85.5 B	SOT23-6	COM • NO • GND • IN • n. c. • V+
AAHM	MAX4646EUT	MAX	asw	SPST; R _{ON} < 30 _M ; V _{DD} = 1.85.5 B	SOT23-6	COM • NC • GND • IN • n. c. • V+
AAHO	MAX1736EUT42	MAX	chg	1 x Li+; V _{IN} = 4.7 22 B; V _{OUT} = 4.2 B; I _{CH} < 0.75 mA	SOT23-6	IN • GATE • GND • EN • CT • BATT
AAHP	MAX1605EUT	MAX	vcon	V _{IN} =2.45.5 B; V _{OUT} =0.830 B; I _{CC} <35 mKA	SOT23-6	SHDN • VCC • GND • LX • LIM • FB
AAHQ	MAX4644EUT	MAX	asw	SPDT; R _{DN} < 4.75 Om; V _{DD} = 1.85.5 B	SOT23-6	IN • V+ • GND • NC • COM • NO
AAHR	MAX8880EUT	MAX	reg	LDO; V _{IN} = 2.512 B; V _{DUT} = 1.255 B; I _{DUT} = 200 mA	SOT23-6	IN • GND • OUT • FB • SHDN • POK
AAHS	MAX8881EUT18	MAX	reg	LDO; V _{IN} = 2.5 12 B; V _{DUT} = 1.8 B; I _{DUT} = 200 MA	SOT23-6	IN • GND • OUT • FB • SHDN • POK
AAHT	MAX888 1EUT25	MAX	reg	LDO; V _{IN} = 2.5 12 B; V _{DLT} = 2.5 B; I _{DLT} = 200 MA	SOT23-6	IN • GND • OUT • FB • SHDN • POK
AAHU	MAX8881EUT33	MAX	reg	LDO; V _{IN} = 2.5 12 B; V _{DUT} = 3.3 B; I _{DUT} = 200 MA	SOT23-6	IN • GND • OUT • FB • SHDN • POK
AAHV	MAX8881EUT50	MAX	reg	LDO; V _{IN} = 2.5 12 B; V _{DUT} = 5.0 B; I _{DUT} = 200 MA	SOT23-6	IN • GND • OUT • FB • SHDN • POK
AAHY	MAX6625PMUT	MAX	dts	9-pasp.; T _{AMB} = -55125 °C; I ² C; V _{DD} =35.5B	SOT23-6	SDA • GND • SCL • OT • ADD • VS
AAHZ	MAX6625RMUT	MAX	dts	9-pasp.; T _{AMB} = -55125 °C; I ² C; V _{DD} =35.5B	SOT23-6	SDA • GND • SCL • OT • ADD • VS
AAI	MAX2654EXT	MAX	amp	$V_{CC} = 2.75.5 \text{ B; f}_P = 1575 \text{ M}\Gamma\text{U; I}_{CC} \le 9.2 \text{ mA}$	SOT363, SC88	GND • GND • RFIN • VCC • GND • RFOUT
AAIA	MAX3190EUT	MAX	tmsmit	RS-232; V_{CC} = $\pm 7.5\pm 12$ В; f_{DR} = 460 Кбит/с; I_{CC} < 250 мкА	SOT23-6	SHDN • GND • TIN • TOUT • VEE • VCC
AAIE	MAX4561EUT	MAX	asw .	SPDT; R _{DN} < 750m; V _{DD} = 1.812 B	SOT23-6	IN • V+ • GND • NC • COM • NO
AAIJ	MAX9030AUT	MAX	cmp	R-R; V _{DSI} < ±5 mB; V _{DD} = 2.55.5 B; I _{DD} < 55 mkA	SOT23-6	IN+ • VSS • IN- • OUT • SHDN • VDD
AAIK	MAX6329SHUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 3.3 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAIL	MAX6329SLUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{DUT} = 3.3 B; I _{DUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAIM	MAX6329SPUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 3.3 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAIN	MAX6329THUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{DUT} = 3.3 B; I _{DUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAIO	MAX6329TLUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 3.3 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAIP	MAX6329TPUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 3.3 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAIQ	MAX6329VHUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 1.8 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAIR	MAX6329VLUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 1.8 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAIS	MAX6329VPUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 1.8 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAIT	MAX6329WHUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 1.8 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAIU	MAX6329WLUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{DUT} = 1.8 B; I _{DUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAIV	MAX6329WPUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 1.8 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
MIAA	MAX6329YHUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 2.5 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAIX	MAX6329YLUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 2.5 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAIY	MAX6329YPUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 2.5 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAIZ	MAX6329ZHUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 2.5 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAJ	MAX2655EXT	MAX	amp	$V_{CC} = 2.75.5 \text{ B; } f_P = 1575 \text{ M} \Gamma_{\text{U; }} I_{CC} \le 9.2 \text{ mA}$	SOT363, SC88	BIAS • GND • RFIN • VCC • GND • RFOUT
ALAA	MAX6329ZLUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 2.5 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAJB	MAX6329ZPUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 2.5 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • SHDN • RES • SET • OUT
AAJC	MAX6349SHUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{DUT} = 3.3 B; I _{DUT} > 150 mA	SOT23-6	IN • GND • MR • RES • SET • OUT
AAJD	MAX6349SLUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 3.3 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • MR • RES • SET • OUT
AAJE	MAX6349SPUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 3.3 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • MR • RES • SET • OUT
AAJF	MAX6349THUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 3.3 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • MR • RES • SET • OUT
AAJG	MAX6349TLUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5B; V _{DUT} = 3.3B; I _{DUT} > 150 mA	SOT23-6	IN • GND • MR • RES • SET • OUT
AAJH	MAX6349TPUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{DUT} = 3.3 B; I _{DUT} > 150 mA	SOT23-6	IN • GND • MR • RES • SET • OUT
ILAA	MAX6349VHUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 1.8B; I _{OUT} > 150 MA	SOT23-6	IN • GND • MR • RES • SET • OUT
AAJJ	MAX6349VLUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{DUT} = 1.8 B; I _{DUT} > 150 mA	SOT23-6	IN • GND • MR • RES • SET • OUT
AAJK	MAX6349VPUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5B; V _{OUT} = 1.8B; I _{OUT} > 150 MA	SOT23-6	IN • GND • MR • RES • SET • OUT



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
\AJL	MAX6349WHUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 1.8B; I _{OUT} > 150 mA	SOT23-6	IN • GND • MR • RES • SET • OUT
MLAA	MAX6349WLUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 1.8 B; I _{OUT} > 150 MA	SOT23-6	IN • GND • MR • RES • SET • OUT
NLA	MAX6349WPUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{DUT} = 1.8 B; I _{DUT} > 150 mA	SOT23-6	IN • GND • MR • RES • SET • OUT
OLA	MAX6349YHUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 2.5 B; I _{OUT} > 150 MA	SOT23-6	IN • GND • MR • RES • SET • OUT
ALP	MAX6349YLUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 2.5 B; I _{OUT} > 150 MA	SOT23-6	IN • GND • MR • RES • SET • OUT
AJQ.	MAX6349YPUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 2.5 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • MR • RES • SET • OUT
\AJR	MAX6349ZHUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 2.5 B; I _{OUT} > 150 MA	SOT23-6	IN • GND • MR • RES • SET • OUT
AJS	MAX6349ZLUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{DUT} = 2.5 B; I _{DUT} > 150 MA	SOT23-6	IN • GND • MR • RES • SET • OUT
AJT	MAX6349ZPUT	MAX	reg + mrc	LDO; V _{IN} = 2.55.5 B; V _{DUT} = 2.5 B; I _{OUT} > 150 mA	SOT23-6	IN • GND • MR • RES • SET • OUT
WLA	MAX6339AUT	MAX	mrc	V _{IN1} =5B; V _{IN2} =3.3B; V _{IN3} =2.5B; V _{IN4} =per.; V _{DD} =1.05.5B; I _{CC} <115mkA	SOT23-6	IN1 • IN2 • IN3 • IN4 • GND • RES
VLA.	MAX6339BUT	MAX	mrc	V _{IN1} = 5B, V _{IN2} = 3.3 B; V _{IN3} = 2.5 B; V _{IN4} = per.; V _{DD} = 1.05.5B; I _{CC} < 115 mkA	SOT23-6	IN1 • IN2 • IN3 • IN4 • GND • RES
WLAJ	MAX6339CUT	MAX	mrc	V_{IN1} = 5B; V_{IN2} = 3.3 B; V_{IN3} = 1.8B; V_{IM4} = per.; V_{DD} = 1.05.5B; I_{CC} < 115 mkA	SOT23-6	IN1 • IN2 • IN3 • IN4 • GND • RES
oon o	MAX6339DUT	MAX	mrc	V_{IN1} = 5B; V_{IN2} = 3.3 B; V_{IN3} = 1.8B; V_{IN4} = per.; V_{DD} = 1.05.5B; I_{CC} < 115 mkA	30.000.000.000	IN1 • IN2 • IN3 • IN4 • GND • RES
	MAX6339EUT	MAX	mrc	V_{IN1} =5B; V_{IN2} =3B; V_{N3} =2.5B; V_{IN4} =per.; V_{DD} =1.05.5B; I_{CC} <115mkA		IN1 • IN2 • IN3 • IN4 • GND • RES
	MAX6339FUT	MAX	mrc	V _{IN1} =5B; V _{IN2} =3B; V _{N3} =2.5B; V _{IN4} =per; V _{DD} =1.05.5B; I _{CC} <115 mkA	000000000000000000000000000000000000000	IN1 • IN2 • IN3 • IN4 • GND • RES
5,535	MAX2656EXT	MAX	amp	V _{CC} = 2.75.5 В; f _P = 1960 МГц; I _{CC} < 9.2 мА	SC88	BIAS • GND • RFIN • VCC • GND • RFOUT
20.000	MAX6339GUT	MAX	mrc	V _{IN1} =5B; V _{IN2} =3B; V _{N3} =1.8B; V _{IN4} =per; V _{DD} =1.05.5B; I _{CC} <115 mkA	.552.5	IN1 • IN2 • IN3 • IN4 • GND • RES
	MAX6339HUT	MAX	mrc	V_{IN1} = 5B; V_{IN2} = 3B; V_{N3} = 1.8B; V_{IN4} = per; V_{DD} = 1.05.5B; I_{CC} < 115 мкA		IN1 • IN2 • IN3 • IN4 • GND • RES
	MAX6339IUT	MAX	mrc	$V_{\text{IN1}} = 5B$; $V_{\text{IN2}} = 3.3B$; $V_{\text{N3}} = 2.5B$; $V_{\text{IN4}} = 1.8B$; $V_{\text{DD}} = 1.05.5B$; $I_{\text{CC}} \le 115$ mkA		IN1 • IN2 • IN3 • IN4 • GND • RES
	MAX6339JUT	MAX	mrc	$V_{IN1} = 5B$; $V_{IN2} = 3.3$ B; $V_{IN3} = 2.5$ B; $V_{IIM} = 1.8$ B; $V_{DD} = 1.05.5$ B; $I_{CC} < 115$ MKA	10.00.000	IN1 • IN2 • IN3 • IN4 • GND • RES
	MAX6339KUT	MAX	mrc	V _{IN1} = per.; V _{IN2} = 3.3 B; V _{IN3} = 2.5 B; V _{IN4} = per.; V _{DD} = 1.05.5 B; I _{CC} < 115 мкА		IN1 • IN2 • IN3 • IN4 • GND • RES
2.5	MAX6339LUT	MAX	mrc	V _{IN1} = per.; V _{IN2} = 3.3 B; V _{IN3} = 2.5 B; V _{IN4} = per.; V _{ID} = 1.05.5 B; I _{CC} < 115 m/A		IN1 • IN2 • IN3 • IN4 • GND • RES
	MAX6339MUT	MAX	mrc	V _{IN1} = 5B; V _{IN2} = 3B; V _{IN3} = per; V _{IN4} = -5B; V _{DD} = 1.05.5B; I _{CC} < 115 MrA		IN1 • IN2 • IN3 • IN4 • GND • RES
	MAX6339NUT MAX6339OUT	MAX	mrc	$V_{IN1} = 5B; V_{IN2} = 3B; V_{IN3} = per; V_{IN4} = -5B;$ $V_{DD} = 1.05.5B; I_{CC} < 115mkA$ $V_{IN1} = 5B; V_{IN2} = 3.3B; V_{IN3} = per; V_{IN4} = -5B;$	100000000	IN1 • IN2 • IN3 • IN4 • GND • RES IN1 • IN2 • IN3 • IN4 • GND • RES
302(2)	MAX6339PUT	MAX	mrc	V _{DD} =1.05.5B; I _{CC} <115мкА	4.0000000000000000	IN1 • IN2 • IN3 • IN4 • GND • RES
355.00	MAX6505UTN035		tempsw	V _{IN1} =5B; V _{IN2} =3.3B; V _{IN3} =per; V _{IN4} =-5B; V _{ID} =1.05.5B; I _{CC} <115MKA		WARN • GND • S1 • VCC • S0 •
1000	MAX6505UTN030	1001.000		V _{CC} =2.55.5 B; T _{TH} =-35°C; I _{CC} <80 mKA	1222000 0	ALARM
332		00000	tempsw	V _{CC} = 2.5 5.5 B; T _{TH} = -30 °C; I _{CC} < 80 mKA	100000000000000000000000000000000000000	WARN • GND • S1 • VCC • S0 • ALARM
30,330	MAX6505UTN025		tempsw	V _{CC} = 2.55.5 B; T _{TH} = -25°C; I _{CC} < 80 mKA	100000000000000000000000000000000000000	WARN • GND • S1 • VCC • S0 • ALARM
	MAX6505UTN020		tempsw	V _{CC} =2.55.5 B; T _{TH} =-20°C; I _{CC} < 80 мкA		WARN • GND • S1 • VCC • S0 • ALARM
	MAX6505UTN015		tempsw	$V_{CC} = 2.5 5.5 \text{ B}; T_{TH} = -15 ^{\circ}\text{C}; I_{CC} < 80 \text{ mKA}$		WARN • GND • S1 • VCC • S0 • ALARM
	MAX6505UTN010		tempsw	V _{CC} =2.55.5 B; T _{TH} = -10 °C; I _{CC} < 80 mkA		WARN • GND • S1 • VCC • S0 • ALARM
AKQ	MAX6505UTN005	MAX	tempsw	V _{CC} = 2.55.5 B; T _{TH} = -5 °С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM

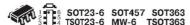




Код	Типономинал	Б	Ф		Особенности	Корпус	Ц: 1•2•3•4•5•6
AAKR	MAX6505UTP000	MAX	tempsw	V _{CC} =2.55	5B; T _{TH} =0°C; I _{CC} <80 mKA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAKS	MAX6505UTP005	MAX	tempsw	V _{CC} = 2.55	5B; T _{TH} =+5°С; I _{CC} <80мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
VAK T	MAX6505UTP010	MAX	tempsw	V _{CC} =2.55	5 В; T _{TH} =+10°С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAKU	MAX6505UTP015	MAX	tempsw	V _{CC} =2.55	5B; T _{TH} =+15°С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAKV	MAX6505UTP020	MAX	tempsw	V _{CC} =2.55	5B; T _{TH} =+20°С; I _{CC} <80мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AKW	MAX6505UTP025	MAX	tempsw	V _{CC} =2.55	5 В; T _{TH} = +25°С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAKX	MAX6505UTP030	MAX	tempsw	V _{CC} =2.55	5 В; T _{TH} = +30°С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAKY	MAX6505UTP035	MAX	tempsw	V _{CC} =2.55	5 В; T _{TH} = +35°С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAKZ	MAX6505UTP040	MAX	tempsw	V _{CC} =2.55	5 В; Т _{ТН} =+40°С; I _{СС} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAL	MAX1852EXT	MAX	vopcon	V _{IN} =2.55.5	B; $f_p = 50 \text{ кГц; } I_{OUT} = 30 \text{ мA}$	SOT363, SC88	OUT • GND • SHDN • IN • C1- • C1-
AALA	MAX6505UTP045	MAX	tempsw	V _{CC} =2.55	5 В; T _{TH} =+45°С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALB	MAX6505UTP050	MAX	tempsw	V _{CC} =2.55	5 В; T _{TH} = +50°С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALC	MAX6505UTP055	MAX	tempsw	V _{CC} =2.55	5 В; T _{TH} =+55°С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALD	MAX6505UTP060	MAX	tempsw	V _{CC} =2.55	5B; T _{TH} =+60°C; I _{CC} < 80 mKA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALE	MAX6505UTP065	MAX	tempsw	V _{CC} =2.55	5 В; T _{TH} =+65°С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALF	MAX6505UTP070	MAX	tempsw	V _{CC} =2.55	5 В; Т _{ТН} =+70°С; I _{СС} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALG	MAX6505UTP075	MAX	tempsw	V _{CC} =2.55	5 В; T _{TH} =+75°С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALH	MAX6505UTP080	MAX	tempsw	V _{CC} =2.55	5B; T _{TH} =+80°C; I _{CC} < 80 mKA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALI	MAX6505UTP085	MAX	tempsw	V _{CC} =2.55	5 В; T _{TH} =+85°С; I _{CC} < 80 мкА	SOT23-6	WARN ● GND ● S1 ● VCC ● S0 ● ALARM
AALJ	MAX6505UTP090	MAX	tempsw	V _{CC} =2.55	5B; T _{TH} =+90°C; I _{CC} <80mkA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALK	MAX6505UTP095	MAX	tempsw	V _{CC} =2.55	5 В; T _{TH} = +95°С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALL	MAX6505UTP100	MAX	tempsw	V _{CC} = 2.55	$5B; T_{TH} = +100C; I_{CC} < 80\text{mKA}$	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALM	MAX6505UTP105	MAX	tempsw	V _{CC} = 2.55	5 В; Т _{тн} =+105°С; I _{CC} <80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALN	MAX6505UTP110	MAX	tempsw	V _{CC} = 2.55	5B; T _{TH} =+110°C; I _{CC} <80 mKA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALO	MAX6505UTP115	MAX	tempsw	V _{CC} =2.55	5 В; Т _{тн} =+115°С; I _{СС} <80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALP	MAX6505UTP120	MAX	tempsw	V _{CC} =2.55	5B; T _{TH} =+120°C; I _{CC} <80 мкA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALQ	MAX6505UTP125	MAX	tempsw	V _{CC} =2.55	5 B; T _{TH} =+125°С; I _{CC} <80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALR	MAX6506UTN035	MAX	tempsw	V _{CC} = 2.55	5 B; T _{TH} =-35°C; I _{CC} <80 mkA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALS	MAX6506UTN030	MAX	tempsw	V _{CC} =2.55	5B; T _{TH} =-30°C; I _{CC} <80 mkA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM



Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
AALT	MAX6506UTN025	MAX	tempsw	$V_{CC} = 2.5 5.5 B; T_{TH} = -25 °C; I_{CC} < 80 mkA$	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALU	MAX6506UTN020	MAX	tempsw	$V_{CC} = 2.5 5.5 B; T_{TH} = -20 °C; I_{CC} < 80 mkA$	S0T23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALV	MAX6506UTN015	MAX	tempsw	$V_{CC} = 2.5 5.5 \text{ B; } T_{TH} = -15 ^{\circ}\text{C; } I_{CC} < 80 \text{ micA}$	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALW	MAX6506UTN010	MAX	tempsw	V _{CC} = 2.55.5 B; T _{TH} = -10 °C; I _{CC} < 80 mkA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALX	MAX6506UTN005	MAX	tempsw	V _{CC} = 2.55.5 B; T _{TH} = -5 °C; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALY	MAX6506UTP000	MAX	tempsw	$V_{CC} = 2.5 5.5 B$; $T_{TH} = 0$ °C; $I_{CC} < 80 \text{ MKA}$	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AALZ	MAX6506UTP005	MAX	tempsw	V _{CC} = 2.55.5 B; T _{TH} = +5 °C; I _{CC} < 80 mkA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAM	MAX1853EXT	MAX	vcpcon	$V_{IN} = 2.55.5 \text{ B}; f_P = 200 \text{ kFu}; I_{OUT} = 30 \text{ mA}$	SOT363, SC88	OUT • GND • SHDN • IN • C1- • C1+
AAMA	MAX6506UTP010	MAX	tempsw	V _{CC} =2.55.5 B; T _{TH} =+10 °С; I _{CC} <80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMB	MAX6506UTP015	MAX	tempsw	V _{CC} =2.55.5 B; T _{TH} =+15 °С; I _{CC} <80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMC	MAX6506UTP020	MAX	tempsw	V _{CC} = 2.55.5 В; Т _{ТН} = +20 °С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMD	MAX6506UTP025	MAX	tempsw	V _{CC} =2.55.5 B; T _{TH} =+25 °C; I _{CC} <80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAME	MAX6506UTP030	MAX	tempsw	V _{CC} = 2.55.5 B; T _{TH} = +30 °C; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMF	MAX6506UTP035	MAX	tempsw	V _{CC} =2.55.5 B; T _{TH} =+35 °C; I _{CC} <80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMG	MAX6506UTP040	MAX	tempsw	V _{CC} = 2.55.5 B; T _{TH} = +40 °C; I _{CC} < 80 mkA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMH	MAX6506UTP045	MAX	tempsw	V _{CC} =2.55.5 В; Т _{ТН} =+45 °С; I _{CC} <80 мкА	S0T23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMI	MAX6506UTP050	MAX	tempsw	V _{CC} = 2.55.5 В; Т _{ТН} = +50 °С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMJ	MAX6506UTP055	MAX	tempsw	V _{CC} = 2.55.5 B; T _{TH} = +55 °С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMK	MAX6506UTP060	MAX	tempsw	V _{CC} = 2.55.5 B; T _{TH} = +60 °C; I _{CC} < 80 mkA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAML	MAX6506UTP065	MAX	tempsw	V _{CC} =2.55.5 B; T _{TH} =+65 °С; I _{CC} <80 мкА	S0T23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMM	MAX6506UTP070	MAX	tempsw	V _{CC} =2.55.5 В; Т _{ТН} = +70 °С; I _{CC} <80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMN	MAX6506UTP075	MAX	tempsw	V _{CC} = 2.55.5 B; T _{TH} = +75 °C; I _{CC} < 80 mKA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMO	MAX6506UTP080	MAX	tempsw	V _{CC} = 2.55.5 В; Т _{ТН} = +80 °С; I _{CC} < 80 мкА	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMP	MAX6506UTP085	MAX	tempsw	V _{CC} = 2.55.5 B; T _{TH} = +85 °C; I _{CC} < 80 mKA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMQ	MAX6506UTP090	MAX	tempsw	V _{CC} = 2.55.5 B; T _{TH} = +90 °C; I _{CC} < 80 mKA	S0T23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMR	MAX6506UTP095	MAX	tempsw	V _{CC} = 2.55.5 B; T _{TH} = +95 °C; I _{CC} < 80 mrA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMS	MAX6506UTP100	MAX	tempsw	V _{CC} =2.55.5 B; T _{TH} =+100 °C; I _{CC} < 80 MKA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMT	MAX6506UTP105	MAX	tempsw	V _{CC} = 2.55.5 B; T _{TH} = +105 °C; I _{CC} < 80 mkA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMU	MAX6506UTP110	MAX	tempsw	V _{CC} =2.55.5 B; T _{TH} =+110 °C; I _{CC} < 80 mkA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
AAMV	MAX6506UTP115	MAX	tempsw	V_{CC} = 2.5 5.5 B; T_{TH} = +115 °C; I_{CC} < 80 m/cA	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
WMAA	MAX6506UTP120	MAX	tempsw	$V_{CC} = 2.55.5 \text{B}; T_{TH} = +120 ^{\circ}\text{C}; I_{CC} < 80 \text{mKA}$	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMX	MAX6506UTP125	MAX	tempsw	$V_{CC} = 2.55.5 \text{ B}; T_{TH} = +125 ^{\circ}\text{C}; I_{CC} < 80 \text{ mKA}$	SOT23-6	WARN • GND • S1 • VCC • S0 • ALARM
AAMY	MAX6507UT8255	MAX	tempsw	$V_{CC} = 2.55.5$ B; $T_{THL} = -80$ °C; $T_{THU} = +85$ °C; $I_{CC} < 60$ MKA	SOT23-6	OK • GND • S0 • VCC • n. c. • OVER
AAMZ	MAX6507UT0A32	MAX	tempsw	$V_{CC} = 2.55.5 B; T_{THL} = +10 °C; T_{THU} = +50 °C; I_{DC} < 60 \text{ MKA}$	SOT23-6	OK • GND • S0 • VCC • n. c. • OVER
AAN	MAX4481AXT	MAX	OA	R-R; V_{DD} = 2.55.5B; I_{CC} < 100 mrA; V_{CS} < 5.5 mB	SOT363, SC88	IN+ • VSS • IN- • OUT • SHDN • VDD
AANA	MAX6508UT8255	MAX	tempsw	$V_{CC} = 2.55.5 B$; $T_{THL} = -80 ^{\circ}C$; $T_{THU} = +85 ^{\circ}C$; $I_{CC} < 60 \text{ MKA}$	SOT23-6	OK • GND • S0 • VCC • n. c. • OVER
AANB	MAX6508UT0A32	MAX	tempsw	$V_{CC} = 2.55.5$ B; $T_{THL} = +10$ °C; $T_{THU} = +50$ °C; $I_{DC} < 60$ MKA	SOT23-6	OK • GND • S0 • VCC • n. c. • OVER
AANC	MAX1736EUT41	MAX	chg	1 x Li+; V _{IN} = 4.7 22 B; V _{DLIT} = 4.1 B; I _{CH} < 0.75 mA	SOT23-6	IN • GATE • GND • EN • CT • BATT
AAND	MAX4675EUT	MAX	2SW	SPST; R _{ON} < 40 _M ; V _{DD} = 2.75.5/±2.7±5.5B	SOT23-6	V+ • COM • V- • GND • NO • IN
AANE	MAX4676EUT	MAX	asw	SPST; R _{DN} < 40 _M ; V _{DD} = 2.75.5/±2.7±5.5 B	SOT23-6	V+ • COM • V- • GND • NC • IN
AANF	MAX1818EUT25	MAX	reg	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 2.5/1.255B; I _{OUT} = 500 mA	SOT23-6	IN • POK • SHDN • GND • SET • OUT
AANG	MAX1818EUT33	MAX	reg	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 3.3/1.255B; I _{DUT} = 500 mA	SOT23-6	IN • POK • SHDN • GND • SET • OUT
AANH	MAX1818EUT50	MAX	reg	LDO; V _{IN} =2.55.5 B; V _{OUT} =5.0/1.255B; I _{DIT} =500 mA	SOT23-6	IN • POK • SHDN • GND • SET • OUT
AANI	MAX6351LRUT	MAX	mrc	$V_{TR1} = 4.63B$; $V_{TR2} = 2.63B$; $V_{DO} = 1.25.5B$; $I_{DC} < 50$ MKA	SOT23-6	RST1 • GND • MR • VCC2 • RST2 • VCC1
AANL	MAX1755BAUT	MAX	ltemp	SMBus; V _{CC} = 2.3755.5B; T _{THAC} = ±3 °C; I _{CC} < 200 mKA	SOT23-6	ADD • SMBDATA • SMBCLK • OVERT • VCC • GND
AANM	MAX1755AAUT	MAX	ltcmp	SMBus; V _{CC} = 2.3755.5B; T _{THAC} = ± 3 °C; I _{CC} < 200 мкA	SOT23-6	ADD • SMBDATA • SMBCLK • OVERT • VCC • GND
AANN	MAX1756BAUT	MAX	ltemp	SMBus; $V_{CC} = 2.3755.5B$; $T_{THAC} = \pm 3$ °C; $I_{CC} < 200$ mKA	SOT23-6	ADD • SMBDATA • SMBCLK • ALERT • VCC • GND
AANO	MAX1756AAUT	MAX	ltcmp	SMBus; V _{CC} = 2.3755.5B; T _{THAC} = ± 3 °C; I _{CC} < 200 мкA	SOT23-6	ADD • SMBDATA • SMBCLK • ALERT • VCC • GND
AANP	MAX6626PMUT	MAX	dts	12-pasp.; T _{AMB} = -55125 °C; I ² C; V _{DD} =35.5 B	SOT23-6	SDA • GND • SCL • OT • ADD • VS
AANQ	MAX6626RMUT	MAX	dts	12-pasp.; T _{AMB} = -55125 °C; I ² C; V _{DD} =35.5 B	SOT23-6	SDA • GND • SCL • OT • ADD • VS
AANT	MAX6355MRUT	MAX	mrc	$V_{TR1} = 4.38 B$; $V_{TR2} = 2.63 B$; $V_{DO} = 1.25.5 B$; $I_{CC} < 50 \text{ MKA}$	SOT23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AANU	MAX1818EUT18	MAX	reg	LDO; V _{IN} = 2.5 5.5 B; V _{OUT} = 1.8/1.25 5B; I _{DUT} = 500 mA	SOT23-6	IN • POK • SHDN • GND • SET • CUT
AANV	MAX1818EUT20	MAX	reg	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 2.0/1.255B; I _{OUT} = 500 mA	SOT23-6	IN • POK • SHDN • GND • SET • OUT
WAAA	MAX1836EUT50	MAX	vcon	V _{IN} =4.524 B; V _{DUT} =5B; I _{DUT} <125 mA	SOT23-6	FB • GND • IN • LX • SHDN • OUT
AANX	MAX1837EUT50	MAX	vcon	V _{IN} =4.524B; V _{DUT} =5B; I _{DUT} <250 mA	SOT23-6	FB • GND • IN • LX • SHDN • OUT
AANY	MAX1836EUT33	MAX	vcon	V _{IN} =4.524 B; V _{DUT} =3.3B; I _{DUT} <125 mA	SOT23-6	FB • GND • IN • LX • SHDN • OUT
AANZ	MAX1837EUT33	MAX	vcon	V _{IN} = 4.524 B; V _{DUT} = 3.3 B; I _{DUT} < 250 mA	SOT23-6	FB • GND • IN • LX • SHDN • OUT
AAO	MAX3371EXT	MAX	levtrans	RS-232; V_{CC} = 2.55.5B; f_{DR} = 2Мбит/c; I_{CC} < 100 мкА	SOT363, SC88	VL • GND • I/O VL • I/O VCC • SHDN • VCC
AAOA	MAX6511UT045	MAX	tempsw	$V_{CC} = 3.0 5.5 \text{ B}; T_{TH} = +45 ^{\circ}\text{C}; I_{CC} < 600 \text{ MKA}$	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOB	MAX6511UT055	MAX	tempsw	$V_{CC} = 3.0 5.5 B; T_{TH} = +55 C; I_{CC} < 600 \text{mKA}$	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AACC	MAX6511UT065	MAX	tempsw	$V_{CC} = 3.05.5 \text{B}; T_{TH} = +65 ^{\circ}\text{C}; I_{CC} < 600 \text{mKA}$	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOD	MAX6511UT075	MAX	tempsw	V_{CC} = 3.0 5.5 B; T_{TH} = +75 °C; I_{CC} < 600 MKA	SOT23-6	VDD • GND • HYST • TOVER • DXN •



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
AAOE	MAX6511UT085	MAX	tempsw	V _{CC} =3.05.5 B; T _{TH} =+85 °C; I _{CC} <600 mkA	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOF	MAX6511UT095	MAX	tempsw	V _{CC} =3.05.5 B; T _{TH} =+95 °C; I _{CC} <600 mkA	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOG	MAX6511UT105	MAX	tempsw	$V_{CC} = 3.0 5.5 \text{ B}; T_{TH} = +105 ^{\circ}\text{C}; I_{CC} < 600 \text{ MKA}$	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOH	MAX6511UT115	MAX	tempsw	$V_{CC} = 3.05.5 \text{B}; T_{TH} = +115 ^{\circ}\text{C}; I_{CC} < 600 \text{mKA}$	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOI	MAX6511UT125	MAX	tempsw	$V_{CC} = 3.0 5.5 \text{ B}; T_{TH} = +125 ^{\circ}\text{C}; I_{CC} < 600 \text{ mKA}$	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOJ	MAX6512UT045	MAX	tempsw	V _{CC} = 3.05.5 B; T _{TH} = +45 °C; I _{CC} < 600 мкА	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOK	MAX6512UT055	MAX	tempsw	V _{CC} =3.05.5 B; T _{TH} =+55 °C; I _{CC} <600 mKA	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOL	MAX6512UT065	MAX	tempsw	V _{CC} =3.05.5 В; Т _{ТН} = +65 °С; I _{CC} <600 мкА	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOM	MAX6512UT075	MAX	tempsw	V _{CC} =3.05.5 B; T _{TH} =+75 °C; I _{CC} <600 mKA	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAON	MAX6512UT085	MAX	tempsw	$V_{CC} = 3.0 5.5 \text{ B; } T_{TH} = +85 \text{ 'C; } I_{CC} < 600 \text{ MKA}$	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOO	MAX6512UT095	MAX	tempsw	V _{CC} =3.05.5 B; T _{TH} =+95 °C; I _{CC} <600 mkA	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOP	MAX6512UT105	MAX	tempsw	V_{CC} = 3.05.5 B; T_{TH} = +105 °C; I_{CC} < 600 MKA	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOQ	MAX6512UT115	MAX	tempsw	$V_{CC} = 3.0 5.5 B; T_{TH} = +115 ^{\circ}C; I_{CC} < 600 \text{mKA}$	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOR	MAX6512UT125	MAX	tempsw	$V_{CC} = 3.0 5.5 \text{ B}; T_{TH} = +125 \text{ °C}; I_{CC} < 600 \text{ MKA}$	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAOS	MAX4481AUT	MAX	OA	R-R; V _{DD} = 2.55.5 B; I _{CC} < 100 mkA; V _{DSI} < 5.5 mB	SOT23-6	IN+ • VSS • IN- • OUT • SHDN • VDD
TOAA	MAX1832EUT	MAX	vcon	V _{IN} = 1.55.5 B; V _{OUT} = 25.5 B; I _{DUT} < 150 mA	SOT23-6	SHDN • BATT • GND • LX • OUT • FB
AAOU	MAX1833EUT	MAX	vcon	V _{IN} = 1.55.5 B; V _{OUT} = 3.3 B; I _{OUT} < 150 mA	SOT23-6	SHDN • BATT • GND • LX • OUT • RST
AAOV	MAX1834EUT	MAX	vcon	V _{IN} = 1.55.5 B; V _{OUT} = 25.5 B; I _{OUT} < 150 mA	SOT23-6	SHDN • BATT • GND • LX • OUT • FB
AAOW	MAX1835EUT	MAX	vcon	V _{IN} = 1.55.5 B; V _{OUT} = 3.3 B; I _{OUT} < 150 mA	SOT23-6	SHDN • BATT • GND • LX • OUT • RST
AAOX	MAX1522EUT	MAX	bcontr	V _{CC} = 2.55.5 B; I _{CC} < 50 mKA; T _{AMB} = -4085°C	SOT23-6	GND • FB • SET • SHDN • EXT • VCC
AAOY	MAX1523EUT	MAX	bcontr	V _{CC} = 2.55.5 B; I _{CC} < 50 mKA; T _{AMB} = -4085 °C	SOT23-6	GND • FB • SET • SHDN • EXT • VCC
AAOZ	MAX1524EUT	MAX	bcontr	V _{CC} = 2.55.5 B; I _{CC} < 50 mKA; T _{AMB} = -4085°C	SOT23-6	GND • FB • SET • SHDN • EXT • VCC
ДДР	MAX5461EXT	MAX	Dpot	32 позиции; 100кОм; V _{DD} = 2.75.5 В	SOT363, SC88	VDD • GND • U/D • CS • L • H
AAPD	MAX6513UT045	MAX	tempsw	V _{CC} =3.05.5 B; T _{TH} =+45 °C; I _{CC} <600 мкA	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAPE	MAX6513UT055	MAX	tempsw	V _{CC} =3.05.5 B; T _{TH} = +55 °C; I _{CC} < 600 мкА	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAPF	MAX6513UT065	MAX	tempsw	V _{CC} =3.05.5 B; T _{TH} =+65 °C; I _{CC} <600 мкA	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAPG	MAX6513UT075	MAX	tempsw	V _{CC} =3.05.5 B; T _{TH} =+75 °C; I _{CC} <600 mkA	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAPH	MAX6513UT085	MAX	tempsw	V _{CC} =3.05.5 B; T _{TH} = +85 °C; I _{CC} < 600 мкА	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAPI	MAX6513UT095	MAX	tempsw	V _{CC} =3.05.5 B; T _{TH} =+95 °C; I _{CC} <600 mKA	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AARJ	MAX6513UT105	MAX	tempsw	V _{CC} =3.05.5 B; T _{TH} =+105 °C; I _{CC} <600 mkA	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAPK	MAX6513UT115	MAX	tempsw	V _{CC} = 3.05.5 B; T _{TH} = +115 °C; I _{CC} < 600 MKA	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP

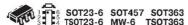




Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
AAPL	MAX6513UT125	MAX	tempsw	V _{CC} =3.05.5 B; T _{TH} =+125 °C; I _{CC} <600 MKA	SOT23-6	VDD • GND • HYST • TOVER • DXN • DXP
AAPM	MAX6629MUT	MAX	dts	12-раар.+ знак; Т _{АМВ} = -55125 °C; SPI; V _{DD} =35.5 В; I _{CC} = 200 мкА	SOT23-6	n. c. • GND • VCC • SCK • CS • SO
AAPN	MAX6630MUT	MAX	dts	12-разр.+ знак; Т _{АМВ} = -55125 °C; SPI; V _{DD} =35.5B; I _{CD} =200 мкА	SOT23-6	GND • n. c. • VCC • SCK • CS • S0
AAPO	MAX6631MUT	MAX	dts	12-разр.+знак; Т _{АМВ} = -55125 °C; SPI; V _{DD} =35.5B; I _{CD} =30 мкА	SOT23-6	n. c. • GND • VCC • SCK • CS • S0
AAPP	MAX6632MUT	MAX	dts	12-разр.+ знак; Т _{АМВ} = -55125 °C; SPI; V _{DD} =35.5B; I _{CD} = 30 мкА	SOT23-6	GND • n. c. • VCC • SCK • CS • SO
AAPQ	MAX6826SUT	MAX	mrc + wdt	$V_{TR} = 2.93 \text{ B; } V_{DD} = 1.25.5 \text{ B; } I_{CC} < 30 \text{ mkA}$	SOT23-6	RES • GND • MR • WDI • RES IN • VCC
AAPR	MAX6827RUT	MAX	mrc + wdt	$V_{TR} = 2.63 \text{ B}; V_{DD} = 1.25.5 \text{ B}; I_{CC} < 30 \text{ mKA}$	SOT23-6	RES • GND • MR • WDI • RES IN • VCC
AAPS	MAX6828YUT	MAX	mrc + wdt	V _{TR} =2.19 B; V _{DD} =1.25.5 B; I _{CC} < 30 mkA	SOT23-6	RES • GND • MR • WDI • RES IN • VCC
AAPT	MAX6829SVUT	MAX	mrc + wdt	$V_{TR1} = 2.93 B$; $V_{TR2} = 1.575 B$; $V_{DD} = 1.25.5 B$; $I_{CC} < 30 \text{ MKA}$	SOT23-6	RES • GND • MR • WDI • VCC2 • VCC
AAPU	MAX6830ZGUT	MAX	mrc + wdt	$V_{TR1} = 2.32B$; $V_{TR2} = 1.11B$; $V_{DO} = 1.25.5B$; $I_{CC} < 30 \text{ MKA}$	SOT23-6	RES • GND • MR • WDI • VCC2 • VCC
AAPV	MAX6831VDUT	MAX	mrc + wdt	$V_{TR1} = 1.58 B$; $V_{TR2} = 0.788 B$; $V_{DD} = 1.25.5 B$; $I_{CC} < 30 \text{ MKA}$	SOT23-6	RES • GND • MR • WDI • VCC2 • VCC
AAQ	MAX5462EXT	MAX	Dpot	32 повиции; 100 кОм; V _{DO} = 2.75.5 В	SOT363, SC88	VDD • GND • U/D • CS • W • H
AAQA	MAX6351UVUT	MAX	mrc	$V_{TR1} = 2.78B$; $V_{TR2} = 1.58B$; $V_{DO} = 1.25.5B$; $I_{CO} \le 50$ MKA	SOT23-6	RST1 • GND • MR • VCC2 • RST2 • VCC1
AAQB	MAX6358RWUT	MAX	mrc	V _{TR1} = 2.63B; V _{TR2} = 1.67B; V _{DD} = 1.25.5B; I _{CD} < 50 MKA	SOT23-6	RST • GND • MR • VCC2 • WDI • VCC1
AAQC	MAX6359TWUT	MAX	mrc	V _{TR1} = 2.93B; V _{TR2} = 2.19B; V _{DD} = 1.25.5B; I _{CD} < 50 MKA	SOT23-6	RST • GND • MR • VCC2 • WDI • VCC1
AAQD	MAX6360RVUT	MAX	mrc	$V_{TR1} = 2.63B$; $V_{TR2} = 1.58B$; $V_{DO} = 1.25.5B$; $I_{CC} < 50$ MKA	SOT23-6	RST • GND • MR • VCC2 • WDI • VCC1
AAQE	MAX6355TVUT	MAX	mrc	$V_{TR1} = 3.08B$; $V_{TR2} = 1.58B$; $V_{DO} = 1.25.5B$; $I_{CC} < 50$ MKA	SOT23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AAQF	MAX6356SWUT	MAX	mrc	$V_{TR1} = 2.93B$; $V_{TR2} = 1.67B$; $V_{DO} = 1.25.5B$; $I_{CC} < 50$ mKA	SOT23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AAQG	MAX6357UVUT	MAX	mrc	$V_{TR1} = 2.78B$; $V_{TR2} = 1.58B$; $V_{DD} = 1.25.5B$; $I_{CC} < 50$ MKA	SOT23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AAQH	MAX6355TYUT	MAX	mrc	$V_{TR1} = 3.08B; V_{TR2} = 2.19B; V_{DO} = 1.25.5B; I_{CC} < 50 \text{ MKA}$	SOT23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AAQJ	MAX5900AAEUT	MAX	hscontr	$V_{EE} = -1009 \text{ B; } I_{CC} < 1.3 \text{ mA; } V_{CB} = 200 \text{ mB}$	SOT23-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AAQK	MAX5900ABEUT	MAX	hscontr	V _{EE} =-1009B; I _{CC} <1.3 mA; V _{CB} =300 mB	SOT23-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AAQL	MAX5900ACEUT	MAX	hscontr	$V_{EE} = -1009 \text{ B; } I_{CC} < 1.3 \text{ mA; } V_{CB} = 400 \text{ mB}$	SOT23-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AAQM	MAX5900LAEUT	MAX	hscontr	V _{EE} =-1009B; I _{CC} <1.3mA; V _{CB} =200 mB	SOT23-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AAQN	MAX5900LBEUT	MAX	hscontr	V _{IE} =-1009B; I _{CC} <1.3mA; V _{CB} =300 mB	SOT23-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AAQO	MAX5900LCEUT	MAX	hscontr	V _{EE} =-1009B; I _{CC} <1.3mA; V _{CB} =400 mB	SOT23-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AAQP	MAX5901AAEUT	MAX	hscontr	$V_{EE} = -1009 \text{ B}; I_{CC} < 1.3 \text{ mA}; V_{CB} = 200 \text{ mB}$	SOT23-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AAQQ	MAX5901ABEUT	MAX	hscontr	V _{EE} =-1009 B; I _{CC} < 1.3 mA; V _{CB} =300 mB	SOT23-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AAQR	MAX5901ACEUT	MAX	hscontr	V _{IE} = -1009B; I _{CC} < 1.3 mA; V _{CB} = 400 mB	SOT23-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
AAQS	MAX5901LAEUT	MAX	hscontr	V _{EE} = -1009 B; I _{CC} < 1.3 mA; V _{CB} = 200 mB	SOT23-6	VEE ◆ DRAIN ◆ GATE ◆ GND ◆ PGOOD ◆ ON/OFF
AAQT	MAX5901LBEUT	MAX	hscontr	$V_{EE} = -1009 \text{ B; } I_{CC} < 1.3 \text{ mA; } V_{CB} = 300 \text{ mB}$	SOT23-6	VEE • DRAIN • GATE • GND • PGCOD • ON/OFF
AAQU	MAX5901LCEUT	MAX	hscontr	V _{EE} = -1009 B; I _{CC} < 1.3 mA; V _{CB} = 400 mB	SOT23-6	VEE ◆ DRAIN ◆ GATE ◆ GND ◆ PGOOD ◆ ON/OFF
AAQV	MAX5900NNEUT	MAX	hscontr	V _{EE} = -1009 B; I _{CC} < 1.3 mA	SOT23-6	VEE • DRAIN • GATE • GND • PGCOD • ON/OFF
	MAX5901NNEUT	MAX	hscontr	V _{EE} =-1009B; I _{CC} < 1.3mA		VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AAQX	MAX6826TUT	MAX	mrc + wdt	V _{TR} =3.08 B; V _{DD} =1.25.5 B; I _{CC} <30 мкА	SOT23-6	RES • GND • MR • WDI • RES IN • VCC
AAQY	MAX6827LUT	MAX	mrc + wdt	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} <30 мкА	SOT23-6	RES • GND • MR • WDI • RES IN • VCC
AAQZ	MAX6829SHUT	MAX	mrc + wdt	$V_{TR1} = 2.93 \text{ B}; V_{TR2} = 1.313 \text{ B}; V_{DO} = 1.25.5 \text{ B}; V_{CC} < 30 \text{ m/sA}$	SOT23-6	RES • GND • MR • WDI • VCC2 • VCC
AAR	MAX5464EXT	MAX	Dpot	32 позиции; 50 кОм; V _{DO} = 2.75.5 В	SOT363, SC88	VDD•GND•U/D•CS•L•H
AARA	MAX6830YGUT	MAX	mrc + wdt	$V_{TR1} = 2.19 \text{ B}; V_{TR2} = 1.11 \text{ B}; V_{DD} = 1.25.5 \text{ B}; $ $I_{CC} \le 30 \text{ MKA}$	SOT23-6	RES • GND • MR • WDI • VCC2 • VCC
AARB	MAX6323CUT46	MAX	mrc	V_{TR} =4.63 B; V_{D0} =1.25.5 B; I_{CC} <57 mKA	SOT23-6	MR • GND • WDI • VCC • WDPO • RES
AARC	MAX6324HUT31	MAX	mrc	V _{TR} =3.00 B; V _{DD} =1.25.5 B; I _{CC} <57 мкА	SOT23-6	MR • GND • WDI • VCC • WDPO • RES
AARD	MAX6323FUT23	MAX	mrc	V _{TR} =2.25 B; V _{DD} =1.25.5 B; I _{CC} <57 mKA	SOT23-6	MR • GND • WDI • VCC • WDPO • RES
AARE	MAX6324AUT46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} <57мкА	S0T23-6	MR • GND • WDI • VCC • WDPO • RES
AARF	MAX6819UT	MAX	vseq	V _{TR} =0.62 B; V _{CC} =0.95.5 B; I _{CC} <120 mKA	SOT23-6	VCC1 • GND • SETV • EN • GATE • VCC2
AARG	MAX6820UT	MAX	vseq	V _{TR} =0.62 B; V _{CC} =0.95.5 B; I _{CC} <120 mKA	SOT23-6	VCC1 • GND • SETV • SETD • GATE • VCC2
AARH	MAX5467EUT	MAX	Doot	32 позиции; 10 кОм; V _{DO} = 2.75.5 В	SOT23-6	VDD • GND • U/D • CS • L • H
AARI	MAX5468EUT	MAX	Dpot	32 позиции; 10 кОм; V _{DO} = 2.75.5B	SOT23-6	VDD • GND • U/D • CS • W • H
AARJ	MAX6323AUT29	MAX	mrc	V _{TR} =2.93 B; V _{DO} =1.25.5 B; I _{CC} < 57 mKA	SOT23-6	MR • GND • WDI • VCC • WDPO • RES
AARK	MAX6351RVUT	MAX	mrc	$V_{TR1} = 2.63 \text{ B}; V_{TR2} = 1.58 \text{ B}; V_{DD} = 1.25.5 \text{ B}; V_{DC} < 50 \text{ mKA}$	SOT23-6	RST1 • GND • MR • VCC2 • RST2 • VCC1
AARL	MAX6356RWUT	MAX	mrc	$V_{TR1} = 2.63 \text{ B}; V_{TR2} = 1.67 \text{ B}; V_{DD} = 1.25.5 \text{ B}; $ $I_{CC} < 50 \text{ MKA}$	S0T23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AARM	MAX6357UWUT	MAX	mrc	$V_{TR1} = 2.78 \text{ B}; V_{TR2} = 1.67 \text{ B}; V_{DD} = 1.25.5 \text{ B}; V_{CC} < 50 \text{ mKA}$	SOT23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AARIN	MAX6358TWUT	MAX	mrc	$V_{TR1} = 2.93 \text{ B}; V_{TR2} = 2.19 \text{ B}; V_{DD} = 1.25.5 \text{ B}; V_{CC} < 50 \text{ mKA}$	SOT23-6	RST • GND • MR • VCC2 • WDI • VCC1
AARO	MAX6358SVUT	MAX	mrc	$V_{TR1} = 2.93 \text{ B}; V_{TR2} = 1.58 \text{ B}; V_{DD} = 1.25.5 \text{ B}; V_{CC} < 50 \text{ MKA}$	SOT23-6	RST • GND • MR • VCC2 • WDI • VCC1
AARP	MAX6359RVUT	MAX	mrc	$V_{TR1} = 2.63 \text{ B}; V_{TR2} = 1.58 \text{ B}; V_{DD} = 1.25.5 \text{ B}; V_{CC} < 50 \text{ MKA}$	S0T23-6	RST • GND • MR • VCC2 • WDI • VCC1
AARQ	MAX6360SWUT	MAX	mrc	$V_{TR1} = 2.93 \text{ B}; V_{TR2} = 1.67 \text{ B}; V_{DO} = 1.25.5 \text{ B}; $ $I_{CC} < 50 \text{ MKA}$	SOT23-6	RST • GND • MR • VCC2 • WDI • VCC1
AARR	MAX6355RWUT	MAX	mrc	$V_{TR1} = 2.63 \text{ B}; V_{TR2} = 1.67 \text{ B}; V_{DD} = 1.25.5 \text{ B};$ $I_{CC} \le 50 \text{ MKA}$	S0T23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AARS	MAX6356UVUT	MAX	mrc	$V_{TR1} = 2.78 \text{ B}; V_{TR2} = 1.58 \text{ B}; V_{DD} = 1.25.5 \text{ B}; V_{DD} = 5.00 \text{ MKA}$	SOT23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AART	MAX6359UVUT	MAX	mrc	$V_{TR1} = 2.78 \text{ B}; V_{TR2} = 1.58 \text{ B}; V_{DD} = 1.25.5 \text{ B}; V_{DC} < 50 \text{ MKA}$	S0T23-6	RST • GND • MR • VCC2 • WDI • VCC1
AARU	MAX9109EUT	MAX	cmp	V _{DS} < 4 mB; V _{CC} = 4.55.5 B; I _{CC} < 0.7 mA	SOT23-6	OUT • GND • IN+ • IN- • LE • VCC
AARV	MAX4647EUT	MAX	asw	SPST; R _{DM} < 300m; V _{DD} = 936/±4.5±20B	SQT23-6	NC • V- • IN • GND • V+ • COM





Код	Типономинал	5	ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
AARW	MAX4648EUT	MAX	asw	SPST; R _{DN} < 30 Om; V _{DD} = 936/±4.5±20 B	SOT23-6	NO • V- • IN • GND • V+ • COM
AARX	MAX4289EUT	MAX	OA	R-R; V _{DD} = 1.05.5B; I _{CC} < 40 mkA; V _{OSI} < 6 mB	SOT23-6	OUT • GND • IN+ • IN- • n. c. • VCC
AAS	MAX5465EXT	MAX	Dpot	32 повиции; 50 кОм; V _{DD} = 2.75.5 В	SOT363, SC88	VDD • GND • U/D • CS • W • H
AASA	MAX5902AAEUT	MAX	hscontr	V _S =+9+72B; I _{CC} <2 mA; V _{CB} =300 mB	SOT23-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AASB	MAX5902ABEUT	MAX	hscontr	V _S =+9+72B; I _{CC} <2 mA; V _{CB} =400 mB	SOT23-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AASC	MAX5902ACEUT	MAX	hscontr	$V_S = +9+72 B; I_{CC} < 2 \text{ mA}; V_{CB} = 500 \text{ mB}$	SOT23-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AASD	MAX5902LAEUT	MAX	hscontr	$V_S = +9+72 B; I_{CC} < 2 \text{ mA}; V_{CB} = 300 \text{ mB}$	SOT23-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AASE	MAX5902LBEUT	MAX	hscontr	V _S =+9+72B; I _{CC} <2 mA; V _{CB} =400 mB	SOT23-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AASF	MAX5902LCEUT	MAX	hscontr	$V_S = +9+72 B$; $I_{CC} < 2 \text{ mA}$; $V_{CB} = 500 \text{ mB}$	SOT23-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AASG	MAX5903AAEUT	MAX	hscontr	V _S =+9+72B; I _{CC} <2 mA; V _{CB} =300 mB	SOT23-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AASH	MAX5903ABEUT	MAX	hscontr	$V_S = +9+72 B; I_{CC} < 2 \text{ mA}; V_{CB} = 400 \text{ mB}$		VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AASI	MAX5903ACEUT	MAX	hscontr	V _S =+9+72B; I _{CC} <2 mA; V _{CB} =500 mB		VS • DRAIN • GATE • GND • PGOOD • ON/OFF
	MAX5903LAEUT	MAX	hscontr	$V_S = +9+72 B; I_{CC} < 2 \text{ mA}; V_{CB} = 300 \text{ mB}$		VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AASK	MAX5903LBEUT	MAX	hscontr	$V_S = +9+72 B; I_{CC} < 2 \text{ mA}; V_{CB} = 400 \text{ mB}$		VS • DRAIN • GATE • GND • PGOOD • ON/OFF
	MAX5903LCEUT	MAX	hscontr	$V_S = +9+72 B; I_{CC} < 2 \text{ mA}; V_{CB} = 500 \text{ mB}$	SOT23-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AASM	MAX5902NNEUT	MAX	hscontr	V _S =+9+72B; I _{CC} < 2 mA	SOT23-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
	MAX5903NNEUT	MAX	hscontr	V _S =+9+72B; I _{CC} <2 mA	SOT23-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AASO	MAX1818EUT15	MAX	reg	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 1.5/1.255B; I _{DUT} = 500 mA	SOT23-6	IN • POK • SHDN • GND • SET • CU
AASP	MAX6355MSUT	MAX	mrc	$V_{TR1} = 4.38 B; V_{TR2} = 2.93 B; V_{DD} = 1.25.5 B; I_{CC} < 50 \text{mkA}$	SOT23-6	RST • GND • MR • VCC2 • RSTIN • VCC1
AASQ	MAX5021EUT	MAX	PWM	V _{IN} =1128 B; DT < 50%; I _{CC} < 2.43 mkA	SOT23-6	CS • GND • NDRV • VCC • VIN • OPTO
AASR	MAX5022EUT	MAX	PWM	V _{IN} =1128 B; DT < 70%; I _{CC} < 2.43 MKA	SOT23-6	CS • GND • NDRV • VCC • VIN • OPTO
AAT	MAX1474AXT	MAX	flecap	C = 6.413.3 пФ; цифровой интерфейс; V _{DD} = 4.55.5 В	SOT363, SC88	CP • VDD • EN • DAT • VSS • CM
AAU	MAX9109EXT	MAX	cmp	V _{DSI} < 4 mB; V _{CC} = 4.55.5 B; I _{CC} < 0.7 mA	SOT363, SC88	CUT • GND • IN+ • IN- • LE • VCC
AAV	MAX4380EXT	MAX	OA	R-R; V _{DD} = 4.511/±2.25±5.5 B; f _{BD} = 210 M V _{DSI} < 20 MB	Гц; SOT363, SC88	CUT • VEE • IN+ • IN- • DISABLE • VCC
AAXH	MAX6033CAUT25	MAX	vref	V _{IN} = 2.712.6 B; AC < ±0.1 %; V _{DUT} = 2.500 B	SOT23-6	i. c. ●GND ● i. c. ● IN ● OUTF ● OUTS
IXA/	MAX6033CAUT30	MAX	vref	V _{IN} = 2.712.6 B; AC < ±0.1 %; V _{OUT} = 3.000 B	SOT23-6	i. c. •GND • i. c. • IN • OUTF • OUTS
LXA	MAX6033CAUT41	MAX	vref	V _{IN} =2.712.6 B; AC < ±0.1 %; V _{OUT} =4.096 B	SOT23-6	i. c. •GND • i. c. • IN • OUTF • OUTS
AAXK	MAX6033CAUT50	MAX	vref	V _{IN} =2.712.6 B; AC < ±0.1 %; V _{DUT} =5.000 B	SOT23-6	i. c. • GND • i. c. • IN • OUTF • OUTS
4AXL	MAX6033BAUT25	MAX	vref	V _{IN} =2.712.6 B; AC < ±0.2 %; V _{OUT} = 2.500 B	SOT23-6	i. c. •GND • i. c. • IN • OUTF • OUTS
MXAA	MAX6033BAUT30	MAX	vref	V _{IN} = 2.712.6 B; AC < ±0.2 %; V _{DUT} = 3.000 B	SOT23-6	i. c. • GND • i. c. • IN • OUTF • OUTS
AAXN	MAX6033BAUT41	MAX	vref	V _{IN} =2.712.6 B; AC < ±0.2 %; V _{OUT} =4.096 B	SOT23-6	i. c. •GND • i. c. • IN • OUTF • OUTS
OXAA	MAX6033BAUT50	MAX	vref	V _{IN} =2.712.6 B; AC < ±0.2 %; V _{DUT} =5.000 B	SOT23-6	i. c. • GND • i. c. • IN • OUTF • OUTS
ABDF	MAX6033AAUT25	MAX	vref	V _{IN} =2.712.6 B; AC < ±0.04%; V _{OUT} = 2.500 B	SOT23-6	i. c. • GND • i. c. • IN • OUTF • OUTS
ABDG	MAX6033AAUT30	MAX	vref	V _{IN} =2.712.6 B; AC < ±0.04%; V _{OUT} = 3.000 B		i. c. •GND • i. c. • IN • OUTF • OUT



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
ABDH	MAX6033AAUT41	MAX	vref	V _{IN} = 2.712.6 B; AC < ±0.04%; V _{OUT} = 4.096 B	SOT23-6	i. c. • GND • i. c. • IN • OUTF • OUTS
ABDI	MAX6033AAUT50	MAX	vref	V _{IN} = 2.712.6 B; AC < ±0.04%; V _{OUT} = 5.000 B	SOT23-6	i. c. • GND • i. c. • IN • OUTF • OUTS
ABEC	MAX5048AAUT	MAX	drv	КМОП-вход; V _{CC} = 412.6B; I _{DUT} < 7.6/1.3A	SOT23-6	V+•P_OUT•N_OUT•GND•IN-• IN+
ABED	MAX5048BAUT	MAX	drv	ТТЛ-вход; V _{CC} = 412.6B; I _{OUT} < 7.6/1.3A	SOT23-6	V+•P_OUT•N_OUT•GND•IN-•
ABQS	MAX3190EEUT	MAX	trnsmit	RS-232; V_{CC} =±7.5±12 B; f_{DR} =460K6ит/c; I_{CC} <250 мкA	SOT23-6	SHDN • GND • TIN • TOUT • VEE • VCC
AD0	ADS1100A0IDBV	TI	ADC	16-разр.; I ² C; адрес 100 1000; V _{DD} = 2.75.5 В	SOT23-6	VIN+ • GND • SCL • SDA • VDD • VIN-
AD1	ADS1100A1IDBV	П	ADC	16-разр.; РС; адрес 1001001; V _{D0} = 2.75.5 В	SOT23-6	VIN+ • GND • SCL • SDA • VDD • VIN-
AD2	ADS1100A2IDBV	TI	ADC	16-разр.; РС; адрес 100 1010; V ₀₀ = 2.75.5 В	SOT23-6	VIN+ • GND • SCL • SDA • VDD • VIN-
AD3	ADS1100A3IDBV	П	ADC	16-разр.; I ² C; адрес 100 1011; V ₀₀ = 2.75.5 В	SOT23-6	VIN+ • GND • SCL • SDA • VDD • VIN-
AD4	ADS1100A4IDBV	TI	ADC	16-разр.; I ² C; адрес 1001100; V _{DD} =2.75.5 В	SOT23-6	VIN+ • GND • SCL • SDA • VDD • VIN-
AD5	ADS1100A5IDBV	П	ADC	16-разр.; РС; адрес 1001101; V ₀₀ =2.75.5 В	SOT23-6	VIN+ • GND • SCL • SDA • VDD • VIN-
AD6	ADS1100A6IDBV	TI	ADC	16-разр.; РС; адрес 1001110; V ₀₀ = 2.75.5 В	SOT23-6	VIN+ • GND • SCL • SDA • VDD • VIN-
AD7	ADS1100A7IDBV	TI	ADC	16-разр.; РС; адрес 1001111; V ₀₀ =2.75.5 В	SOT23-6	VIN+ • GND • SCL • SDA • VDD • VIN-
AK	HSMS280K	HP	shd x2	$V_{BB} > 70 \text{ B; } V_F (I_F = 15 \text{ mA}) < 1.0 \text{ B; } I_B (V_B = 50 \text{ B}) < 200 \text{ HA; } C_D < 2.0 \text{ n}\Phi$	SOT363, SC88	A1 • n. c. • A2 • K2 • n. c. • K1
AL	HSMS280L	HP	shd x3	$V_{BB} > 70 \text{ B; } V_F (I_F = 15 \text{ mA}) < 1.0 \text{ B; } I_B (V_B = 50 \text{ B}) < 200 \text{ nA; } C_D < 2.0 \text{ n}\Phi$	SOT363, SC88	A1 • A2 • A3 • K3 • K2 • K1
AM	HSMS280M	HP	shd x4	$V_{BB} > 70 \text{ B; } V_F (I_F = 15 \text{ mA}) < 1.0 \text{ B; } I_B (V_B = 50 \text{ B}) < 200 \text{ HA; } C_D < 2.0 \text{ n}\Phi$	SOT363, SC88	A1 • K1, K2, K3, K4 • A2 • A3 • K1, K2, K3, K4 • A4
AN	HSMS280N	HP	shd x4	$V_{BB} > 70 \text{ B}; V_F (I_F = 15 \text{ mA}) < 1.0 \text{ B}; I_B (V_B = 50 \text{ B}) < 200 \text{ hA}; C_D < 2.0 \text{ n}\Phi$	SOT363, SC88	K1 • A1, A2, A3, A4 • K2 • K3 • A1, A2, A3, A4 • K4
AP	HSMS280P	HP	shd x4	$V_{BB} > 70 \text{ B; } V_F (I_F = 15 \text{ mA}) < 1.0 \text{ B; } I_R (V_B = 50 \text{ B}) < 200 \text{ HA; } C_D < 2.0 \text{ n}\Phi$	SOT363, SC88	A1 • K1, A2 • K2 • K3 • K4,A3 • A4
B1	IMB1A	ROHM	Dpnp x2	$V_{DC} = 50 \text{ B; } I_{DUT} = 30 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} > 56; 22 \text{ KOm}/22 \text{ KOM}$	SOT23-6	C1 • B2 • E2 • C2 • B1 • E1
B1	UMB1N	ROHM	Dpnp x2	$V_{CC} = 50 \text{ B; } I_{OUT} = 30 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} > 56; 22 \text{ KOM/} 22 \text{ KOM}$	SOT363, SC88	E1•B1•C2 •E2•B2 •C1
B10	EMB10	ROHM	Dpnp x2	$V_{CC} = 50 \text{ B; } I_{DUT} = 100 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} > 80; \\ 2.2 \text{ kOm}/47 \text{ kOm}$	SOT563, EMT6	E1•B1•C2 •E2•B2 •C1
B10	IMB10A	ROHM	Dpnp x2	V_{CC} = 50 B; I_{DUT} = 100 mA; P_D = 300 mBT; $h_{21} > 80$; 2.2 kOm/47 kOm	SOT23-6	C1 • B2 • E2 • C2 • B1 • E1
B10	UMB10N	ROHM	Dpnp x2	$V_{CC} = 50 \text{ B; } I_{DUT} = 100 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} > 80; \\ 2.2 \text{ kOm}/47 \text{ kOm}$	SOT363, SC88	E1•B1•C2 •E2•B2 •C1
B11	EMB11	ROHM	Dpnp x2	$V_{CC} = 50 \text{ B; } I_{DUT} = 100 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} > 30; \\ 10 \text{ kOm}/10 \text{ kOm}$	SOT563, EMT6	E1 • B1 • C2 • E2 • B2 • C1
B11	IMB11A	ROHM	Dpnp x2	$V_{CC} = 50 \text{ B; } I_{DUT} = 100 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} > 30; \\ 10 \text{ KOm} / 10 \text{ KOM}$	SOT23-6	C1 • B2 • E2 • C2 • B1 • E1
B11	UMB11N	ROHM	Dpnp x2	$V_{CC} = 50 \text{ B; } I_{OUT} = 100 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} > 30; \\ 10 \text{ kOm}/10 \text{ kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
B 16	IMB16	ROHM	Dpnp x2	$V_{DC} = 50 \text{ B; } I_{DUT} = 500 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} > 30; R2/R1 = 2.1$	SOT23-6	C1 • B2 • E2 • C2 • B1 • E1
B17	IMB17A	ROHM	Dpnp x2	$V_{CC} = 50 \text{ B; } I_{OUT} = 100 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} > 33; $ R2/R1 = 10	SOT23-6	C1 • B1 • C2 • B2 • E2 • E1
B2	EMB2	ROHM	Dpnp x2	V_{DC} = 50 B; I_{DUT} = 30 mA; P_D = 150 mBT; h_{21} > 68; 47 kOm/47 kOm	SOT563, EMT6	E1 • B1 • C2 • E2 • B2 • C1
B2	IMB2A	ROHM	Dpnp x2	V _{CC} = 50 B; I _{OUT} = 30 мА; P _D = 300 мВт; h ₂₁ > 68; 47 кОм/47 кОм	SOT23-6	C1 •B2 •E2 •C2 •B1 •E1

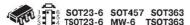




Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
32	UMB2N	ROHM	Dpnp x2	V_{DC} = 50 B; I_{OUT} = 30 mA; P_D = 150 mBT; h_{21} > 68; 47 kOm/47 kOm	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
33	EMB3	ROHM	Dpnp x2	$V_{\rm CC}$ = 50 B; $I_{\rm OUT}$ = 100 mA; $P_{\rm D}$ = 150 mBT; $h_{\rm 21}$ > 100; $R_{\rm 1}$ 4.7 kOm	SOT563, EMT6	E1 • B1 • C2 • E2 • B2 • C1
33	IMB3A	ROHM	Dpnp x2	V_{CC} = 50 B; I_{OUT} = 100 mA; P_D = 300 mBT; h_{21} > 100; R_1 4.7 kOm	SOT23-6	C1•B2 •E2•C2 •B1•E1
33	UMB3N	ROHM	Dpnp x2	V_{CC} = 50 B; I_{OUT} = 100 mA; P_D = 150 mBT; h_{21} > 100; R_1 4.7 kOm	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
34	EMB4	ROHM	Dpnp x2	V_{CC} = 50 B; I_{OUT} = 100 mA; P_D = 150 mBT; h_{21} > 100; R_1 10 кОм	SOT563, EMT6	E1 • B1 • C2 • E2 • B2 • C1
34	IMB4A	ROHM	Dpnp x2	V_{CC} = 50 B; I_{OUT} = 100 mA; P_D = 300 mB τ ; h_{21} > 100; R_1 10 kOm	SOT23-6	C1•B2 •E2•C2 •B1•E1
34	UMB4N	ROHM	Dpnp x2	V_{CC} = 50 B; I_{OUT} = 100 mA; P_D = 150 mBT; h_{21} > 100; R_1 10 кОм	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
35	IMB5A	ROHM	Dpnp x2	V_{CC} = 50 B; I_{OUT} = 100 mA; P_D = 300 mB τ ; h_{21} > 56; R2/R1 = 1	SOT23-6	C1•B1•C2•B2 •E2•C1
35	UMB5N	ROHM	Dpnp x2	V _{CC} =50 B; I _{OUT} = 100 mA; P _D = 150 mBr; h ₂₁ > 56; R2/R1 = 22 kOm/22 kOm	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
36	EMB6	ROHM	Dpnp x2	V_{DC} = 50 B; I_{OUT} = 50 mA; P_D = 150 mBT; h_{21} > 68; R2/R1 = 1	SOT563, EMT6	C1•B1•C2•B2 •E2•E1
36	IMB6A	ROHM	Dpnp x2	V_{DC} = 50 B; I_{OUT} = 50 mA; P_D = 300 mBT; h_{21} > 68; R2/R1 = 1	SOT23-6	C1•B1•C2•B2 •E2•E1
36	UMB6N	ROHM	Dpnp x2	V_{CC} = 50 B; I_{OUT} = 50 mA; P_D = 300 mBT; h_{21} > 68; R2/R1 = 1	SOT363, SC88	C1•B1•C2•B2 •E2•E1
37	IMB7A	ROHM	Dpnp x2	$V_{CC} = 50 \text{ B; } I_{OUT} = 100 \text{ mA; } P_D = 150 \text{ mBr; } h_{21} > 100; \\ R_1 4.7 \text{ KOM}$	SOT23-6	C1•B1•C2•B2 •E2•E1
38	IMB8A	ROHM	Dpnp x2	$V_{DC} = 50 \text{ B}; I_{OUT} = 100 \text{ mA}; P_D = 150 \text{ mBT}; h_{21} > 100; R_1 10 \text{ kOm}$	SOT23-6	C1•B1•C2•B2 •E2•E1
38	UMB8N	ROHM	Dpnp x2	$V_{CC} = 50 \text{ B; } I_{OUT} = 100 \text{ mA; } P_D = 150 \text{ mBr; } h_{21} > 100; \\ R_1 10 \text{ kOm}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
39	EMB9	ROHM	Dpnp x2	$V_{CC} = 50 \text{ B; } I_{OLT} = 70 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} > 100; \\ 10 \text{ k/Om}/47 \text{ k/Om}$	SOT563, EMT6	E1 • B1 • C2 • E2 • B2 • C1
B9	IMB9A	ROHM	Dpnp x2	$V_{DC} = 50 \text{ B; } I_{OUT} = 70 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} > 100; \\ 10 \text{ kOm}/47 \text{ kOm}$	SOT23-6	C1 • B2 • E2 • C2 • B1 • E1
39	UMB9N	ROHM	Dpnp x2	$V_{DC} = 50 \text{ B; } I_{OUT} = 70 \text{ mA; } P_D = 150 \text{ mBt; } h_{21} > 100; \\ 10 \text{ k/Om}/47 \text{ k/Om}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
BAC	ADP3820ART-4.1	AD	chg	Li-Ion; V _{IN} = 4.515B; V _{DUT} = 4.1B	SOT23-6	SD • GND • VOUT • GATE • VIN • IS
BBC	ADP3820ART-4.2	AD	cha	Li-Ion; V _{IN} =4.515B; V _{DLIT} =4.2B	SOT23-6	SD • GND • VOUT • GATE • VIN • IS
3K	HSMS281K	HP	shd x2	$V_{BR} > 20B$; $V_F (I_F = 35 \text{ mA}) < 1.0B$; $I_R (V_B = 15B) < 200 \text{ HA}$; $C_D < 1.2 \text{ n}\Phi$	SOT363, SC88	A1 • n. c. • A2 • K2 • n. c. • K1
3L	HSMS281L	HP	shd x3	$V_{BR} > 20B$; $V_F (I_F = 35 \text{ mA}) < 1.0 B$; $I_B (V_B = 15 B) < 200 \text{ HA}$; $C_D < 1.2 \text{ n}\Phi$	SOT363, SC88	A1 • A2 • A3 • K3 • K2 • K1
3L	MBD54DW	ON	shd x2	$V_R < 30 \text{ B}; V_F (I_F = 10 \text{ mA}) < 0.4 \text{B}; C_D < 10 \text{ n}\Phi$	SOT363, SC88	A1 • n. c. • K2 • A2 • n. c. • K1
206	DDX123JK	DIODS	Dnpn/pnp	V _{CC} = 50 B; I _C = 100 mA; 2.2 k/47 k	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
206	DDX123JU		Dnpn/pnp	V _{CC} =50 B; I _C = 100 mA; 2.2 k/47 k	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
207	DDX143TK	DIODS	Dnpn/pnp	V _{CC} =50 B; I _C =100 mA; R ₁ 4.7 k	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
207	DDX143TU		Dnpn/pnp	$V_{CC} = 50 \text{ B; } I_C = 100 \text{ mA; } R_1 4.7 \text{ K}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
212	DDX114TK	DIODS	Dnpn/pnp	V _{CC} =50 B; I _C =100 мА; R _t 10 к	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
012	DDX114TU		Dnpn/pnp	V _{CC} =50B; I _C =100 mA; R ₁ 10 k		E1 • B1 • C2 • E2 • B2 • C1
213	DDX114EK	DIODS	Dnpn/pnp	V _{CC} =50 B; I _C = 100 mA; 10 к/10 к	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
C13	DDX114EU		Dnpn/pnp	V _{CC} =50B; I _C =100 mA; 10 k/10 k	100000000000000000000000000000000000000	E1 • B1 • C2 • E2 • B2 • C1
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Код	Типономинал	6	Ф	Особенности	Kopnyc	ц: 1•2•3•4•5•6
C14	DDX114YU	DIODS	Dnpn/pnp	$V_{CC} = 50 \text{ B; } I_C = 100 \text{ mA; } 10 \text{ k/} 47 \text{ k}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
217	DDX124EK	DIODS	Dnpn/pnp	V _{CC} = 50 B; I _C = 100 mA; 22 k/22 k	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
C17	DDX124EU	DIODS	Dnpn/pnp	$V_{CC} = 50 \text{ B; } I_C = 100 \text{ mA; } 22 \text{ k/} 22 \text{ k}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
220	DDX144EK	DIODS	Dnpn/pnp	$V_{CC} = 50 \text{ B; } I_C = 100 \text{ mA; } 47 \text{ k/} 47 \text{ k}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
220	DDX144EU	DIODS	Dnpn/pnp	$V_{CC} = 50 \text{ B; } I_C = 100 \text{ mA; } 47 \text{ k}/47 \text{ k}$	SOT363, SC88	E1•B1•C2•E2•B2•C1
C2T	AD7466BRTZ	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DO} = 1.63.6B	SOT23-6	VDD • GND • VIN • SCLK • SDATA • CS
C410	ZXSC410	ZETEX	vcon	V _{CC} = 1.658.0B; I _{OUT} = 300 mA	SOT23-6	VCC • GND • STDN • SENSE • VFB • DRIVE
C420	ZXSC420	ZETEX	vcon	V _{DC} = 1.658.0B; I _{DUT} = 300 mA	SOT23-6	VCC • GND • EOR • SENSE • VFB • DRIVE
C55	OPA355NA	П	OA	R-R; V_{DD} = 2.75.5 B; f_{BD} = 200 MFu; I_S = 14 mA; V_{DS} < ±15 mB	SOT23-6	OUT • V- • +IN • -IN • ENBL • V+
CAA	AD7814ART	AD	dts	10-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.75.5B	SOT23-6	GND • DIN • VDD • SCLK • CS • DOUT
CEW	AD7476AYKS	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V ₀₀ = 2.355.25 B	SOT363, SC88	VDD • GND • VIN • SCLK • SDATA • CS
CEY	AD7476ABKS	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.355.25 B	SOT363, SC88	VDD • GND • VIN • SCLK • SDATA • CS
CEZ	AD7476AAKS	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V ₀₀ = 2.355.25 B	SOT363, SC88	VDD • GND • VIN • SCLK • SDATA • CS
CFZ	AD7477AAKS	AD	ADC	10-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.355.25 B	SOT363, SC88	VDD • GND • VIN • SCLK • SDATA • CS
CHA	AD7414ART	AD	dts	10-разр.; SMBus/I ² C; V ₀₀ =2.75.5В	SOT23-6	AS • GND • VDD • SCL • ALERT • SDA
СНВ	AD7414ART	AD	dts	10-разр.; SMBus/I ² C; V ₀₀ =2.75.5В	SOT23-6	AS • GND • VDD • SCL • ALERT • SDA
CHC	AD7414ART	AD	dts	10-разр., SMBus/I ² C; V ₀₀ =2.75.5В	SOT23-6	AS • GND • VDD • SCL • ALERT • SDA
CHD	AD7414ART	AD	dts	10-разр.; SMBus/I ² C; V ₀₀ =2.75.5В	SOT23-6	AS • GND • VDD • SCL • ALERT • SDA
CJZ	AD7478AAKS	AD	ADC	8-pasp.; SPI/QSPI/Microwire; V ₀₀ = 2.35 5.25B	SOT363, SC88	VDD • GND • VIN • SCLK • SDATA • CS
CK	HSMS282K	HP	shd x2	$V_{BR} > 15 B$; $V_F (I_F = 30 \text{ mA}) < 0.7 B$; $I_B (V_B = 1 B) < 100 \text{ mA}$; $C_T < 1.0 \text{ n}\Phi$; $R_D = 120 \text{ m}$	SOT363, SC88	A1 • n. c. • A2 • K2 • n. c. • K1
CL	HSMS282L	HP	shd x3	$V_{BR} > 15 B$; $V_F (I_F = 30 \text{ mA}) < 0.7 B$; $I_B (V_B = 1 B) < 100 \text{ mA}$; $C_T < 1.0 \text{ mD}$; $R_D = 120 \text{ m}$	SOT363, SC88	A1 • A2 • A3 • K3 • K2 • K1
CLB	AD7466BRT	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} = 1.6 3.6B	SOT23-6	VDD • GND • VIN • SCLK • SDATA • CS
CMB	AD7467BRT	AD	ADC	10-pasp.; SPI/QSPI/Microwire; V _{DD} = 1.6 3.6B	SOT23-6	VDD • GND • VIN • SCLK • SDATA • CS
CMU	AD7467BRTZ	AD	ADC	10-разр.; SPI/QSPI/Microwire; V _{DD} = 1.6 3.6 В	SOT23-6	VDD • GND • VIN • SCLK • SDATA • CS
CNA	AD7466ART	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} = 1.6., 3.6B	SOT23-6	VDD • GND • VIN • SCLK • SDATA • CS
CNB	AD7468BRT	AD	ADC	8-pasp.; SPI/QSPI/Microwire; V ₀₀ = 1.63.6 B	SOT23-6	VDD • GND • VIN • SCLK • SDATA • CS
CNU	AD7468BRTZ	AD	ADC	8-pasp.; SPI/QSPI/Microwire; V ₀₀ = 1.63.6 B	SOT23-6	VDD • GND • VIN • SCLK • SDATA • CS
сР	µPA873TD	NEC	npn x2	$V_{CB0} = 9 \text{ B; } I_C = 100 \text{ mA; } P_D = 230 \text{ mBT; } h_{21} = 100 145; f_T > 3 \Gamma \Gamma_{II}$	M16, 1208	C1 • E1 • C2 • E2 • B2 • B1
сР	µPA873TS	NEC	npn x2	$V_{CB0} = 9 \text{ B; } I_C = 100 \text{ mA; } P_D = 230 \text{ mBT; } h_{21} = 100 145; f_T > 3 \Gamma \Gamma I_L$	SOT666	C1 • E1 • C2 • E2 • B2 • B1
CP	HSMS282P	HP	shd x4	$V_{BR} > 15 B$; $V_F (I_F = 30 \text{ mA}) < 0.7 B$; $I_B (V_B = 1 B) < 100 \text{ mA}$; $C_T < 1.0 \text{ nD}$; $R_D = 120 \text{ m}$	SOT363, SC88	A1 • K1, A2 • K2 • K3 • K4, A3 • A4

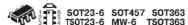




Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
CQA	AD7680ARJ	AD	ADC	16-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.55.5B	SOT23-6	VDD • GND • VIN • SCLK • SDATA • CS
CQB	AD7680BRJ	AD	ADC	16-pasp.; SPI/QSPI/Microwire; V _{DO} = 2.55.5B	SOT23-6	VDD • GND • VIN • SCLK • SDATA • CS
CUA	AD7920AKS	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.355.25 B	SOT363, SC88	VDD • GND • VIN • SCLK • SDATA • CS
CUB	AD7920BKS	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V ₀₀ = 2.355.25 B	SOT363, SC88	VDD • GND • VIN • SCLK • SDATA • CS
CVA	AD7910AKS	AD	ADC	10-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.355.25 B	SOT363, SC88	VDD • GND • VIN • SCLK • SDATA • CS
D1	IMD1A	ROHM	Dpnp/npn	$V_{DC} = 50 \text{ B}; I_{OUT} = 100 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 100; R_1 22 \text{ kOm}$	SOT23-6	C1•B2 •E2•C2 •B1•E1
D10	IMD10A	ROHM	Dpnp/npn	V _{CC} =50 B; I _{OUT1} =500 mA; I _{OUT2} =100 mA; P _D =300 mBT; I ₂₁ >68; 10 kOm/100 kOm	SOT23-6	C1•B2 •E2•C2 •B1•E1
D12	UMD12N	ROHM	Dpnp/npn	$V_{DC} = 50 \text{ B; } I_{OUT} = 100 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} > 68; $ 47 kOm / 47 kOm	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
D14	IMD14	ROHM	Dpnp/npn	V_{DC} =50 B; I_{OUT} =500 mA; P_D =300 mBT; h_{21} >82; R2/R1=45.5	SOT23-6	C1 • B2 • E2 • C2 • B1 • E1
D16	IMD16A	ROHM	Dpnp/npn	V_{CC} = 50 B; I_{OUT} = 500 mA; P_D = 300 mBT; h_{21} > 82; 2.2 kOm/2.2 kOm; R_1 100 kOm	SOT23-6	C1•B2 •E2•C2 •B1•E1
D2	EMD2	ROHM	Dpnp/npn	V _{DC} =50 B; I _{OUT} =30 mA; P _D =150 mBT; h ₂₁ >56; 22 kOm/22 kOm	SOT563, EMT6	E1 • B1 • C2 • E2 • B2 • C1
D2	IMD2A	ROHM	Dpnp/npn	V _{CC} =50 B; I _{OUT} =30 мА; P _D =300 мВт; h ₂₁ >56; 22 кОм/22 кОм	SOT23-6	C1•B2 •E2•C2 •B1•E1
D2	UMD2N	ROHM	Dpnp/npn	V _{CC} = 50 B; I _{OUT} = 500 mA; P _D = 150 mBT; h ₂₁ > 56; 22 kOm/22 kOm	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
D2B	AD5300BRT	AD	DAC	8-pasp.; SPI/Microwire; V ₀₀ = 2.75.5B	SOT23-6	VOUT • GND • VDD • DIN • SCLK • SYNC
D3	EMD3	ROHM	Dpnp/npn	V _{CC} =50 B; I _{OUT} =50 мА; P _D =150 мВт; h ₂₁ >30; 10 кОм/10 кОм	SOT563, EMT6	E1 • B1 • C2 • E2 • B2 • C1
D3	IMD3A	ROHM	Dpnp/npn	V _{CC} =50 B; I _{OLT} =50 мА; P _D =300 мВт; h ₂₁ >30; 10 кОм/10 кОм	SOT23-6	C1 • B2 • E2 • C2 • B1 • E1
D3	UMD3N	ROHM	Dpnp/npn	V _{DC} =50 B; I _{OUT} =50 mA; P _D =150 mBT; h ₂₁ >30; 10 kOm/10 kOm	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
D3B	AD5310BRT	AD	DAC	10-pasp.; SPI/Microwire; V _{DD} = 2.75.5B	SOT23-6	VOUT • GND • VDD • DIN • SCLK • SYNC
D4B	AD5320BRT	AD	DAC	12-pasp.; SPI/Microwire, V _{DD} = 2.75.5B	SOT23-6	VOUT • GND • VDD • DIN • SCLK • SYNC
D6	EMD6	ROHM	Dpnp/npn	V_{DC} =50B; I_{OLT} =100 mA; P_D =150 mBT; h_{21} >100; R_1 4.7 kOm	SOT563, EMT6	E1 • B1 • C2 • E2 • B2 • C1
D6	IMD6A	ROHM	Dpnp/npn	$V_{DC} = 50 \text{ B}; I_{OUT} = 100 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 100; R_1 4.7 \text{ kOM}$	SOT23-6	C1•B2 •E2•C2 •B1•E1
D6	UMD6N	ROHM	Dpnp/npn	V_{CC} =50B; I_{OUT} =100 mA; P_D =150 mBT; h_{21} >100; R_1 4.7 kOm	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
D619	ZXTD09N50DE6	ZETEX	npn x2	V _{CB0} =50 B; I _C =1 A; P _D =900 мВт; h ₂₁ >20; f _T =215 МГц	SOT23-6	C1 • E1 • C2 • B2 • E2 • B1
D8	IMD8A	ROHM	Dpnp/npn	V_{DC} =50B; I_{OLT} =100 mA; P_D =300 mBT; h_{21} >100; R_1 47 кОм	SOT23-6	C1•B2 •E2•C2 •B1•E1
D8B	AD5301BRT	AD	DAC	8-pasp.; I ² C; V _{DD} =2.75.5B	SOT23-6	GND • SDA • SCL • VOUT • A0 • VDD
D9	EMD9	ROHM	Dpnp/npn	V _{CC} =50 B; I _{OUT} = 70 мА; P _D = 150 мВт; h ₂₁ > 100; 10 кОм/47 кОм	SOT563, EMT6	E1 • B1 • C2 • E2 • B2 • C1
D9	IMD9A	ROHM	Dpnp/npn	V _{CC} =50 B; I _{OUT} = 70 мА; P _D = 300 мВт; h ₂₁ > 100; 10 кОм/47 кОм	SOT23-6	C1•B2 •E2•C2 •B1•E1
D9	UMD9N	ROHM	Dpnp/npn	V _{DC} = 50 B; I _{OUT} = 70 мA; P _D = 150 мВт; h ₂₁ > 100; 10 кОм/47 кОм	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
D9B	AD5311BRT	AD	DAC	10-pasp.; I ² C; V _{pp} =2.75.5B	SOT23-6	GND • SDA • SCL • VOUT • A0 • VDD
D9N	AD5320BRTZ	AD	DAC	12-paap.; SPI/Microwire; V _{DO} = 2.75.5 B		VOUT • GND • VDD • DIN • SCLK • SYNC



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
DAB	AD5321BRT	AD	DAC	12-pasp.; I ² C; V _{DD} =2.75.5 B	SOT23-6	GND • SDA • SCL • VOUT • A0 • VDD
F2	RN1903FS	TOSH	Dnpn x2	V _{CB0} = 20 B; I _C = 50 mA; P _D = 50 mBt; B ₁ /B ₂ = 22 kOm/22 kOm	fS6	E1 • B1 • C2 • E2 • B2 • C1
F3	RN1904FS	TOSH	Dnpn x2	V _{CB0} = 20 B; I _C = 50 мА; P _D = 50 мВт; B ₁ /B ₂ = 47 кОм/47 кОм	fS6	E1 • B1 • C2 • E2 • B2 • C1
F4	RN1905FS	TOSH	Dnpn x2	V _{CBD} = 20 B; I _C = 50 мА; P _D = 50 мВт; R ₁ /R ₂ = 2.2 кОм/47 кОм	fS6	E1 • B1 • C2 • E2 • B2 • C1
F5	RN1906FS	TOSH	Dnpn x2	V _{CBD} = 20 B; I _C = 50 мА; P _D = 50 мВт; B ₁ /B ₂ = 4.7 кОм/47 кОм	fS6	E1 • B1 • C2 • E2 • B2 • C1
F 6	RN 1907FS	TOSH	Dnpn x2	V _{CB0} = 20 B; I _C = 50 mA; P _D = 50 mBτ; R ₁ /R ₂ = 10 κ0 m/47 κ0 m	fS6	E1 • B1 • C2 • E2 • B2 • C1
F7	RN1908FS	TOSH	Dnpn x2	V _{CB0} =20B; I _C =50mA; P _D =50 mBτ; R ₁ /R ₂ =22κ0m/47κ0m	fS6	E1 • B1 • C2 • E2 • B2 • C1
F8	RN1909FS	TOSH	Dnpn x2	V _{CB0} = 20 B; I _C = 50 mA; P _D = 50 mBτ; R ₁ /R ₂ = 47 κ0m/22 κ0m	fS6	E1 • B1 • C2 • E2 • B2 • C1
F9	RN1910FS	TOSH	Dnpn x2	V _{CB0} = 20 B; I _C = 50 мA; P _D = 50 мВт; R ₁ = 4.7 кОм	fS6	E1 • B1 • C2 • E2 • B2 • C1
FF	RN1911FS	TOSH	Dnpn x2	V _{CB0} = 20 B; I _C = 50 мA; P _D = 50 мВт; R ₁ = 10 кОм	fS6	E1 • B1 • C2 • E2 • B2 • C1
FF	RN2971FS	TOSH	Dpnp x2	V _{CB0} = 20 B; I _C = 50 mA; P _D = 50 mBT; R ₁ = 10 kOm	fS6	E1 • E2 • B2 • C2 • B1 • C1
GAAI	REG71050DDC	TI	scvcon	V _{IN} = 1.85.5 B; I _{DUT} > 30 mA; V _{DUT} = 5.0 B	TSOT23-	VCUT • GND • ENBL • CPUMP • VIN • CPUMP+
HO.	RN2901FS	TOSH	Dpnp x2	V _{CB0} = 20 B; I _C = 50 мА; P _D = 50 мВт; B ₁ /B ₂ = 4.7 кОм/4.7 кОм	fS6	E1 • B1 • C2 • E2 • B2 • C1
HOE	AD8063ARTZ	AD	OA	f _{BD} =320 МГц; P _D =75 мВт; V _{DD} =2.78 В	SOT23-6	VOUT • -VS • +IN • -IN • DIS • +VS
H1	EMH1	ROHM	Dnpn x2	V _{CBD} =50 B; I _C =30 mA; P _D =150 mB _T ; h ₂₁ >56; 22 kOm/22 kOm	SOT563, EMT6	E1 • B1 • C2 • E2 • B2 • C1
H1	IMH1A	ROHM	Dnpn x2	V_{CBD} =50 B; I_C =30 mA; P_D =300 mBt; h_{21} >56; 22 kOm/22 kOm	SOT23-6	C1 • B1 • B2 • C2 • E2 • E1
H1	RN2902FS	TOSH	D pnp x2	V _{CBD} = 20 B; I _C = 50 мА; P _D = 50 мВт; R ₁ /R ₂ = 10 кОм/10 кОм	fS6	E1 • B1 • C2 • E2 • B2 • C1
H1	UMH1N	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 30 mA; P_D = 150 mBr; h_{21} > 56; 22 kOm/22 kOm	SOT363, SC88	E1•B1•C2 •E2•B2 •C1
H 10	EMH10	ROHM	Dnpn x2	$V_{CBO} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} > 80; \\ 2.2 \text{ kOm}/47 \text{ kOm}$	SOT563, EMT6	E1•B1•C2 •E2•B2 •C1
H10	IMH10A	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 300 mBT; h_{21} > 80; 2.2 kOm/47 kOm	SOT23-6	C1 • B2 • E2 • C2 • B1 • E1
H10	UMH10N	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 150 mBT; h_{21} > 80; 2.2 kOm/47 kOm	SOT363, SC88	E1•B1•C2 •E2•B2 •C1
H 11	EMH11	ROHM	Dnpn x2	V_{CBD} =50 B; I_C =50 mA; P_D =150 mBr; h_{21} >30; 10 kOm/10 kOm	SOT563, EMT6	E1•B1•C2 •E2•B2 •C1
H 11	IMH11A	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 50 mA; P_D = 300 mBr; h_{21} > 30; 10 kOm/10 kOm	SOT23-6	C1 • B1 • B2 • C2 • E2 • E1
H11	UMH11N	ROHM	Dnpn x2	V_{CBD} =50 B; I_C =50 mA; P_D =150 mBr; h_{21} >30; 10 kOm/10 kOm	SOT363, SC88	E1•B1•C2 •E2•B2 •C1
H14	IMH14A	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 300 mBT; h_{21} > 100; R1 47 kOm	SOT23-6	C1 • B1 • B2 • C2 • E2 • E1
H14	UMH14N	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 150 mB1; h_{21} > 100; R1 47 kOm	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
H14	UMH14N	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 150 mBt; h_{21} > 100; R_1 = 47 kOm	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
H 15	IMH15A	ROHM	Dnpn x2	V_{CBO} = 50 B; I_C = 100 mA; P_D = 300 mBr; h_{21} > 100; R1 47 kOm	SOT23-6	C1 • B2 • E2 • C2 • B1 • E1
H2	EMH2	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 30 mA; P_D = 150 mBr; h_{21} > 68; 47 kOm/47 kOm	SOT563, EMT6	E1 • B1 • C2 • E2 • B2 • C1
H2	IMH2A	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 30 mA; P_D = 300 mBr; h_{21} > 68; $47 \text{kOm}/47 \text{kOm}$	SOT23-6	C1 • B1 • B2 • C2 • E2 • E1
H2	RN2903FS	TOSH	Dpnp x2	V _{CBD} = 20 B; I _C = 50 mA; P _D = 50 mBt; R ₁ /R ₂ = 22 kOm/22 kOm	fS6	E1•B1•C2•E2•B2•C1





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
12	UMH2N	ROHM	Dnpn x2	V _{CBD} = 50 B; I _C = 30 мА; P _D = 150 мВт; h ₂₁ > 68; 47 кОм/47 кОм	SOT363, SC88	C1 • B1 • B2 • C2 • E2 • E1
13	ЕМН3	ROHM	Dnpn x2	$V_{CBD} = 50 \text{B}; I_C = 100 \text{mA}; P_D = 150 \text{mB}\tau; h_{21} > 100; R14.7 \text{kOm}$	EMT6	E1 • B1 • C2 • E2 • B2 • C1
13	IMH3A	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 100 мA; P_D = 300 мВт; h_{21} > 100; R14.7 кОм	SOT23-6	C1 • B1 • B2 • C2 • E2 • E1
13	RN2904FS	TOSH	Dpnp x2	V_{CB0} = 20 B, I_C = 50 mA; P_D = 50 mB1; R_1/R_2 = 47 κOm/47 κOm	fS6	E1 • B1 • C2 • E2 • B2 • C1
13	UMH3N	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 150 mBT; h_{21} > 100; R14.7 kOm	SC88	E1 • B1 • C2 • E2 • B2 • C1
14	IMH4A	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 300 mB τ ; h_{21} > 100; R1 10 kOm	SOT23-6	C1 • B2 • E2 • C2 • B1 • E1
14	RN2905FS	TOSH	Dpnp x2	V_{CB0} = 20 B; I_C = 50 mA; P_D = 50 mBT; R_1/R_2 = 2.2 kOm/47 kOm	fS6	E1 • B1 • C2 • E2 • B2 • C1
14	UMH4N	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 150 mB τ ; h_{21} > 100; R110 kOm	SC88	E1 • B1 • C2 • E2 • B2 • C1
15	IMH5A	ROHM	Dnpn x2	V _{CBD} =50 B; I _C =30 mA; P _D =150 mB1; h ₂₁ > 56; 22 kOm/22 kOm	SOT23-6	C1 • B1 • C2 • B2 • E2 • E1
15	MBD770DW	ON	shd x2	$V_R < 70 \text{ B}; V_F (I_F = 10 \text{ mA}) < 1 \text{ B}; C_D < 1 \text{ m}\Phi$	SC88	A1 • n. c. • K2 • A2 • n. c. • K1
1 5	RN2906FS	TOSH	Dpnp x2	V_{CB0} = 20 B; I_C = 50 mA; P_D = 50 mB1; R_1/R_2 = 4.7 kOm/47 kOm	fS6	E1 • B1 • C2 • E2 • B2 • C1
15	UMH5N	ROHM	Dnpn x2	V _{CBD} =50 B; I _C =30 mA; P _D =150 mBr; h ₂₁ >56; 22 kOm/22 kOm	SOT363, SC88	C1 • B1 • C2 • B2 • E2 • E1
16	IMH6A	ROHM	Dnpn x2	V_{CC} = 50 B; I_{OUT} = 30 mA; P_D = 300 mBT; h_{21} > 68; R2/R1 = 1	SOT23-6	C1•B1•C2•B2 •E2•E1
16	RN2907FS	TOSH	Dpnp x2	V _{CBD} =20 B; I _C =50 мА; P _D =50 мВт; R ₁ /R ₂ =10 кОм/47 кОм	fS6	E1 • B1 • C2 • E2 • B2 • C1
16	UMH6N	ROHM	Dnpn x2	V_{CC} =50 B; I_{OUT} =30 mA; P_{D} =300 mB τ ; I_{21} >68; R2/R1 = 1	SOT363, SC88	C1•B1•C2•B2 •E2•E1
16B	AD8029AKS	AD	OA	f _{BD} = 120 МГц; P _D = 18 мВт; V _{DO} = 2.712 В	SOT363, SC88	VOUT • -VS • +IN • -IN • DIS • +VS
17	RN2908FS	TOSH	Dpnp x2	$V_{CB0} = 20 \text{ B}; I_C = 50 \text{ mA}; P_D = 50 \text{ mBr}; R_1/R_2 = 22 \text{ kOm}/47 \text{ kOm}$	fS6	E1 • B1 • C2 • E2 • B2 • C1
48	IMH8A	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 300 mBT; h_{21} > 100; R1 10 kOm	SOT23-6	C1•B1•C2•B2•E2•E1
18	RN2909FS	TOSH	Dpnp x2	V_{CB0} = 20 B; I_C = 50 мA; P_D = 50 мВт; R_1/R_2 = 47 кОм/22 кОм	fS6	E1 • B1 • C2 • E2 • B2 • C1
18	UMH8N	ROHM	Dnpn x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 150 mBT; h_{21} > 100; R1 10 kOm	SC88	E1 • E2 • B2 • C2 • B1 • C1
19	EMH9	ROHM	Dnpn x2	V_{CC} = 50 B; I_{OUT} = 70 mA; P_D = 150 mBT; h_{21} > 68; 10 kOm/47 kOm	SOT563, EMT6	E1 • B1 • C2 • E2 • B2 • C1
19	ІМН9А	ROHM	Dnpn x2	V_{DC} = 50 B; I_{OUT} = 70 mA; P_D = 300 mB τ ; h_{21} > 68; 10 kOm/47 kOm	SOT23-6	C1•B1•E2•C2 •B1•E1
19	RN2910FS	TOSH	Dpnp x2	V _{CB0} = 20 B; I _C = 50 мА; P _D = 50 мВт; R ₁ = 4.7 кОм	fS6	E1 • B1 • C2 • E2 • B2 • C1
19	UMH9N	ROHM	Dnpn x2	V_{DC} = 50 B; I_{OUT} = 70 мA; P_D = 150 мВ τ ; $h_{21} > 68$; 10 кОм/47 кОм	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
lF .	RN2911FS	TOSH	Dpnp x2	V _{CB0} = 20 B; I _C = 50 мA; P _D = 50 мВт; R ₁ = 10 кОм	fS6	E1 • B1 • C2 • E2 • B2 • C1
HH.	HSMS282M	HP	shd x4	$V_{BR} > 15B$; $V_F (I_F = 30 \text{ mA}) < 0.7 \text{ B}$; $I_R (V_R = 18) < 100 \text{ mA}$; $C_T < 1.0 \text{ n}\Phi$; $R_D = 120 \text{ m}$	SOT363, SC88	A1 • K1, K2, K3, K4 • A2 • A3 • K1, K2, K3, K4 • A4
HA	AD8063ART	AD	OA	f _{BD} =320МГц; P _D =75 мВт; V _{DO} =2.78В	SOT23-6	VOUT • -VS • +IN • -IN • DIS • +VS
10	RN1961FS	TOSH	Dnpn x2	V _{CBD} =20 B; I _C =50 mA; P _D =50 mBr; R ₁ /R ₂ =4.7kOm/4.7kOm	fS6	E1 • E2 • B2 • C2 • B1 • C1
1	RN1962FS	TOSH	Dnpn x2	V _{CBD} = 20 B; I _C = 50 mA; P _D = 50 mBt; R ₁ /R ₂ = 10 kOm/10 kOm	fS6	E1 • E2 • B2 • C2 • B1 • C1
12	RN1963FS	TOSH	Dnpn x2	V _{CBD} =20 B; I _C =50 mA; P _D =50 mBT; B ₁ /B ₂ =22 kOm/22 kOm	fS6	E1 • E2 • B2 • C2 • B1 • C1



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
3	RN 1964FS	TOSH	Dnpn x2	V _{CB0} = 20 B; I _C = 50 мА; P _D = 50 мВт; R ₁ /R ₂ = 47 кОм/47 кОм	fS6	E1 • E2 • B2 • C2 • B1 • C1
3A	AD8361ART	AD	PD	$f_{BD} < 2.5 \Gamma \Gamma q$; $P_D = 12 \text{ mBT}$; $V_{DO} = 2.75.5 \text{ B}$	SOT23-6	VRMS • COMM • FLTR • PWDN • RFIN • VPOS
4	RN1965FS	TOSH	Dnpn x2	$V_{CB0} = 20 \text{ B}; I_C = 50 \text{ mA}; P_D = 50 \text{ mBT}; R_1/R_2 = 2.2 \text{ kOm}/47 \text{ kOm}$	fS6	E1 • E2 • B2 • C2 • B1 • C1
J5	RN1966FS	TOSH	Dnpn x2	$V_{CB0} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D = 50 \text{ mBT; } R_1/R_2 = 4.7 \text{ KOm}/47 \text{ KOM}$	fS6	E1 • E2 • B2 • C2 • B1 • C1
J6	RN1967FS	TOSH	Dnpn x2	V _{CB0} = 20 B; I _C = 50 mA; P _D = 50 mBT; R ₁ /R ₂ = 10 κ0m/47 κ0m	fS6	E1 • E2 • B2 • C2 • B1 • C1
J7	RN1968FS	TOSH	Dnpn x2	$V_{CB0} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D = 50 \text{ mBT; } R_1/R_2 = 22 \text{ kOm}/47 \text{ kOm}$	fS6	E1 • E2 • B2 • C2 • B1 • C1
18	RN1969FS	TOSH	Dnpn x2	V _{CB0} = 20 B; I _C = 50 мА; P _D = 50 мВт; R ₁ /R ₂ = 47 кОм/22 кОм	fS6	E1 • E2 • B2 • C2 • B1 • C1
J9	RN1901FS	TOSH	Dnpn x2	$V_{CB0} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D = 50 \text{ mBT; } R_1/R_2 = 4.7 \text{ KOm}/4.7 \text{ KOM}$	fS6	E1 • B1 • C2 • E2 • B2 • C1
J9	RN1970FS	TOSH	Dnpn x2	$V_{CB0} = 20 \text{ B}; I_C = 50 \text{ mA}; P_D = 50 \text{ mB} \text{T}; R_1 = 4.7 \text{ kOm}$	fS6	E1 • E2 • B2 • C2 • B1 • C1
JF	RN1902FS	TOSH	Dnpn x2	$V_{CB0} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D = 50 \text{ mBT; } R_1/R_2 = 10 \text{ kOm}/10 \text{ kOm}$	fS6	E1 • B1 • C2 • E2 • B2 • C1
JF	RN1971FS	TOSH	Dnpn x2	$V_{CB0} = 20 \text{ B}; I_C = 50 \text{ mA}; P_D = 50 \text{ mBT}; R_1 = 10 \text{ kOm}$	fS6	E1 • E2 • B2 • C2 • B1 • C1
JH	RN1972FS	TOSH	Dnpn x2	$V_{CB0} = 20 \text{ B}; I_C = 50 \text{ mA}; P_D = 50 \text{ mBT}; R_1 = 22 \text{ kOm}$	fS6	E1 • E2 • B2 • C2 • B1 • C1
IJ	RN1973FS		Dnpn x2	$V_{CB0} = 20 \text{ B}; I_C = 50 \text{ mA}; P_0 = 50 \text{ mBT}; R_1 = 47 \text{ kOm}$	fS6	E1 • E2 • B2 • C2 • B1 • C1
JSs	BAS21U	INF	dix3	V_B < 200 B; I_F < 250 mA; V_F (I_F = 100 mA) < 1.0 B; I_B < 0.1 mkA	SOT457, SC74	A1 • A2 • A3 • K3 • K2 • K1
K0	RN2961FS	TOSH	Dpnp x2	$V_{CB0} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D = 50 \text{ mBT; } R_1/R_2 = 4.7 \text{ KOm}/4.7 \text{ KOM}$	fS6	E1 • E2 • B2 • C2 • B1 • C1
K1	RN2962FS	TOSH	Dpnp x2	V _{CB0} = 20 B; I _C = 50 мА; P _D = 50 мВт; R ₁ /R ₂ = 10 кОм/10 кОм	fS6	E1 • E2 • B2 • C2 • B1 • C1
K1	UM6K1N	ROHM	nMOSx2	V _{DS} = 30 B; I _D = 100 мА; P _D = 150 мВт; R _{DS(on)} < 13 Ом	SC88	S1•G1•D2•S2•G2•D1
K2	RN2963FS	TOSH	Dpnp x2	V _{CB0} = 20 B; I _C = 50 mA; P _D = 50 mBT; R ₁ /R ₂ = 22 kOm/22 kOm	fS6	E1 • E2 • B2 • C2 • B1 • C1
K3	RN2964FS	TOSH	Dpnp x2	V _{CB0} = 20 B; I _C = 50 мА; Р _D = 50 мВт; R ₁ /R ₂ = 47 кОм/47 кОм	fS6	E1 • E2 • B2 • C2 • B1 • C1
K4	RN2965FS	TOSH	Dpnp x2	$V_{CB0} = 20 \text{ B}; I_C = 50 \text{ mA}; P_D = 50 \text{ mBT}; R1/R2 = 2.2 kOm/47 kOm$	fS6	E1 • E2 • B2 • C2 • B1 • C1
K5	RN2966FS	TOSH	Dpnp x2	$V_{CB0} = 20 \text{ B}; I_C = 50 \text{ mA}; P_D = 50 \text{ mBT}; R_1/R_2 = 4.7 \text{ KOm}/47 \text{ KOm}$	fS6	E1 • E2 • B2 • C2 • B1 • C1
K 6	RN2967FS	TOSH	Dpnp x2	V _{CB0} = 20 B; I _C = 50 mA; P _D = 50 mB1; R ₁ /R ₂ = 10 k0 m/47 k0 m	fS6	E1 • E2 • B2 • C2 • B1 • C1
K7	NCP802SAN5T1	ON	batprot	V _{CC} = 1.55 B; V _{TROU} = 4.275 B	SON-6	DO • Vcell • GND • DS • CO • P
K7	RN2968FS	TOSH	Dpnp x2	$V_{CB0} = 20 \text{ B}; I_C = 50 \text{ mA}; P_D = 50 \text{ mBT}; R1/R2 = 22 kOm/47 kOm$	fS6	E1 • E2 • B2 • C2 • B1 • C1
K7P	BC847PN		pnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBt; } h_{21} = 200475; f_T > 100 \text{MFц}$	SC88	E1 • B1 • C2 • E2 • B2 • C1
K8	RN2969FS	0.000.000.00	Dpnp x2	$V_{CB0} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D = 50 \text{ mBr; } R_1/R_2 = 47 \text{ kOm}/22 \text{ kOm}$	fS6	E1 • E2 • B2 • C2 • B1 • C1
K9	RN2970FS	TOSH	Dpnp x2	$V_{CB0} = 20 \text{ B}; I_C = 50 \text{ mA}; P_D = 50 \text{ mBT}; R_1 = 4.7 \text{ kOm}$	fS6	E1 • E2 • B2 • C2 • B1 • C1
KC1	MMBZ5221BS	DIODS		$V_Z(I_{ZT} = 20 \text{ mA}) = 2.282.52 \text{ B}; I_R < 100 \text{ mKA}$	SC88	A1 • n. c. • K2 • A2 • n. c. • K1
KC3	MMBZ5223BS	DIODS		$V_Z(I_{ZT} = 20 \text{ mA}) = 2.572.84 \text{ B}; I_R < 75 \text{ mKA}$	SC88	A1 • n. c. • K2 • A2 • n. c. • K1
KC5	MMBZ5225BS	DIODS	120000000	$V_Z(I_{ZT} = 20 \text{ mA}) = 2.853.15 \text{ B}; I_R < 50 \text{ mKA}$	SC88	A1 • n. c. • K2 • A2 • n. c. • K1
KD	NCP802SAN6T1	ON	batprot	V _{DC} = 1.55 B; V _{TROU} = 4.28 B	SON-6	DO • Vcell • GND • DS • CO • P
KE1	MMBZ5231BS	DIODS	dz x2	$V_Z(I_{ZT} = 20 \text{ mA}) = 4.855.36 \text{B}; I_R \le 5 \text{ mkA}$	SOT363, SC88	A1 • n. c. • K2 • A2 • n. c. • K1





Код	Типономинал	6	Ф		Особенности		Корпус	ц	1 • 2 • 3 • 4 • 5 • 6
KE2	MMBZ5232BS	DIODS	dz x2	V _Z (I _{ZT} = 2	0 мА) = 5.325.88В; I _R < 5	імкА	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KE3	MMBZ5233BS	DIODS	dz x2	V _Z (I _{ZT} = 2	0 мА) = 5.706.30B; I _R < 5	імкА	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KE4	MMBZ5234BS	DIODS	dz x2	$V_Z(I_{ZT}=2$	0 мА) = 5.896.51 В; I _R < 5	імкА	SOT363, SC88	A1 ● n, c. ● k	(2 • A2 • n. c. • K1
KE5	MMBZ5235BS	DIODS	dz x2	V _Z (I _{ZT} = 2	0 мА) = 6.467.14 B ; I _B < 3	нкА	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KF1	MMBZ5236BS	DIODS	dz x2	V _Z (I _{ZT} = 2	0 мА) = 7.137.88 В; I _R < 3	I мкА	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KF2	MMBZ5237BS	DIODS	dz x2	$V_Z(I_{ZT}=2$	0 мА) = 7.798.61 В ; I _R < 3	I мкА	SOT363, SC88	A1 • n. c. • k	(2 • A2 • n. c. • K1
KF3	MMBZ5238BS	DIODS	dz x2	$V_Z(I_{ZT}=2$	0 мA) = 8.279.14B; I _R < 3	1 мкА	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KF4	MMBZ5239BS	DIODS	dz x2	V _Z (I _{ZT} = 2	0 мA) = 8.659.56 B ; I _B < 3	1 мкА	SOT363, SC88	A1 • n. c. • k	(2 • A2 • n. c. • K1
KF5	MMBZ5240BS	DIODS	dz x2	V _Z (I _{ZT} = 2	0 мА) = 9.510.5В; I _R <3 в	икА	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KG1	MMBZ5226BS	DICDS	dz x2	$V_Z(I_{ZT}=2$	0 мА) = 3.143.47В; I _R < 2	25 mkA	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KG2	MMBZ5227BS	DIODS	dz x2	V _Z (I _{ZT} = 2	0 мA) = 3.423.78B; I _R < 1	5 мкА	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KG3	MMBZ5228BS	DIODS	dz x2	$V_Z(I_{ZT}=2$	0 мA) = 3.714.10B; I _R < 1	ОмкА	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KG4	MMBZ5229BS	DIODS	dz x2	$V_Z(I_{ZT}=2$	0 мА) = 4.094.52 В; I _R < 5	мкА	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KG5	MMBZ5230BS	DIODS	dz x2	V _Z (I _{ZT} = 2	0 mA) = 4.474.94B; I _R < 5	мкА	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
kH	µPA891TD	NEC	npn x2	V _{CB0} =9E h ₂₁ =100	3; I _C = 100 мА; P _D = 230 мВт 160; f _T > 3.5 ГГц	i .	M16, 1208	C1 • E1 • C2	!•B2•E2•B1
KH1	MMBZ5241BS	DIODS	dz x2	V _Z (I _{ZT} = 2	0 мА) = 10.4511.55 В; I _R	< 2 mkA	SOT363, SC88	A1 • n. c. • k	(2•A2•n. c.•K1
KH2	MMBZ5242BS	DIODS	dz x2	V _Z (I _{ZT} = 2	0 мA) = 11.412.6B; I _R <1	мкА	SOT363, SC88	A1 • n. c. • k	(2 • A2 • n. c. • K1
KH3	MMBZ5243BS	DIODS	dz x2	V _Z (I _{ZT} = 9	:5 мА) = 12.3513.65 В; I _В	< 0.5 мкА	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KH5	MMBZ5245BS	DIODS	dz x2	V _Z (I _{ZT} = 8	.5 мА) = 14.2515.75 В; I _В	< 0.1 мкА	SOT363, SC88	A1 • n. c. • k	(2 • A2 • n. c. • K1
KJ1	MMBZ5246BS	DIODS	dz x2	V _Z (I _{ZT} = 7	.8 мА) = 15.216.8 B; I _R < 0	0.1 mkA	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KJ3	MMBZ5248BS	DIODS	dz x2	V _Z (I _{ZT} = 7	.0 мА) = 17.118.9B; I _R < 0	0.1 m KA	SOT363, SC88	A1 • n. c. • k	(2 • A2 • n. c. • K1
KJ5	MMBZ5250BS	DIODS	dz x2	V _Z (I _{ZT} = 8	.2 mA) = 19.021.0 B; I _R < 0	01 мкА	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KK1	MMBZ5251BS	DIODS	dz x2	V _Z (I _{ZT} = 5	.6 мА) = 20.923.1B; I _R <0	0.1 m KA	SOT363, SC88	A1 • n. c. • k	(2 • A2 • n. c. • K1
KK2	MMBZ5252BS	DIODS	dz x2	V _Z (I _{ZT} = 5	.2 mA) = 22.825.2B; I _R < 0	0.1 мкА	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KK4	MMBZ5254BS	DIODS	dz x2	V _Z (I _{ZT} = 5	.0 мА) = 25.6528.35 В; I _В	< 0.1 мкА	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1
KK5	MMBZ5255BS	DIODS	dz x2	V _Z (I _{ZT} = 4	.5 mA) = 26.629.4 B; I _R < 0	0.1 мкА	SOT363, SC88	A1 ● n, c, ●k	(2 • A2 • n. c. • K1
kL	µPA828TD	NEC	npn x2	V _{CB0} =5Ε f _T >7ΓΓυ	3; I _C = 30 мA; P _D = 180 мВт;	h ₂₁ = 70140;	M16, 1208	C1 • E1 • C2	• B2 • E2 • B1
KM1	MMBZ5256BS	DIODS	dz x2	$V_Z(I_{ZT}=4$.2 мА) = 28.531.5 B; I _R < 0	0.1 mkA	SOT363, SC88	A1 • n. c. • k	(2 • A2 • n. c. • K1
KM2	MMBZ5257BS	DIODS	dz x2	$V_Z(I_{ZT} = 3)$.8 мА) = 31.3534.65 В; I _В	< 0.1 mkA	SOT363, SC88	A1 ● n. c. ● k	(2 • A2 • n. c. • K1





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
КМЗ	MMBZ5258BS	DIODS	dz x2	$V_Z(I_{ZT} = 3.4 \text{ mA}) = 34.237.8 \text{ B}; I_R \le 0.1 \text{ mKA}$	SOT363, SC88	A1 • n. c. • K2 • A2 • n. c. • K1
KM4	MMBZ5259BS	DIODS	dz x2	$V_Z(I_{ZT} = 3.2 \text{ mA}) = 37.0541.0 \text{ B}; I_R < 0.1 \text{ mkA}$	SOT363, SC88	A1 • n. c. • K2 • A2 • n. c. • K1
dΝ	µPA892TD	NEC	npn x2	$V_{C80} = 15 \text{ B}; I_C = 35 \text{ mA}; P_D = 210 \text{ mBT}; h_{21} = 50100; f_T > 18 \Gamma \Gamma_{IJ}$	M16, 1208	C1 • E1 • C2 • B2 • E2 • B1
(N	NCP802SAN1T1	ON	batprot	V _{CC} = 1.55B; V _{TROU} = 4.35B	SON-6	DO • Vcell • GND • DS • CO • P
(N	NCP802SN1T1	ON	batprot	V _{CC} = 1.55 B; V _{TROU} = 4.35 B	SOT23-6	DO • P • CO • DS • Vcell • GND
kΡ	µPA895TD	NEC	npn x2	$V_{CB0} = 9 B; I_C = 100 \text{ mA}; P_D = 210 \text{ mBT}; h_{21} = 100145; f_T > 3 \Gamma \Gamma \mu$	M16, 1208	C1 • E1 • C2 • B2 • E2 • B1
⟨P	µPA895TS	NEC	npn x2	$V_{CB0} = 9 B$; $I_C = 100 \text{ mA}$; $P_D = 210 \text{ mBT}$; $I_{D1} = 100145$; $I_{T1} > 3 \Gamma I_{T1}$	SOT666	C1 • E1 • C2 • B2 • E2 • B1
_1B	ADP3330ART-2.5	AD	reg	LDO; V _{IN} = 2.912 B; I _{OUT} = 200 mA; V _{DUT} = 2.5 B	SOT23-6	OUT • IN • ERR • GND • NR • SD
L2B	ADP3330ART- 2.75	AD	reg	LDO; V _{IN} =2.912B; I _{OUT} =200mA; V _{OUT} =2.75B	SOT23-6	OUT • IN • ERR • GND • NR • SD
L3B	ADP3330ART- 2.85	AD	reg	LDO; V _{IN} =2.912B; I _{OUT} =200mA; V _{OUT} =2.85B	SOT23-6	OUT • IN • ERR • GND • NR • SD
.4B	ADP3330ART-3	AD	reg	LDO; V _{IN} = 2.912 B; I _{OUT} = 200 mA; V _{DUT} = 3 B	SOT23-6	OUT • IN • ERR • GND • NR • SD
L5B	ADP3330ART-3.3	AD	reg	LDO; V _{IN} = 2.912 B; I _{OUT} = 200 mA; V _{DUT} = 3.3 B	SOT23-6	OUT • IN • ERR • GND • NR • SD
6B	ADP3330ART-3.6	AD	reg	LDO; V _{IN} = 2.912 B; I _{OUT} = 200 mA; V _{DUT} = 3.6 B	SOT23-6	OUT • IN • ERR • GND • NR • SD
.8B	ADP3330ART-5	AD	reg	LDO; V _{IN} = 2.912 B; I _{OUT} = 200 mA; V _{DUT} = 5 B	SOT23-6	OUT • IN • ERR • GND • NR • SD
L9B	ADP3331ART	AD	reg	LDO; V _{IN} =2.612B; I _{OUT} =200mA; V _{OUT} =1.511.75B	SOT23-6	OUT • IN • ERR • GND • FB • SD
AB	ADP3300ART-2.7	AD	reg	LDO; V _{IN} = 312 B; I _{DUT} = 50 mA; V _{DUT} = 2.7 B	SOT23-6	GND • NR • SD • OUT • IN • ERR
BB	ADP3300ART-3	AD	reg	LDO; V _{IN} = 312 B; I _{DUT} = 50 mA; V _{DUT} = 3 B	SOT23-6	GND • NR • SD • OUT • IN • ERR
CB	ADP3300ART-3.2	AD	reg	LDO; V _{IN} = 312 B; I _{OUT} = 50 mA; V _{OUT} = 3.2 B	SOT23-6	GND • NR • SD • OUT • IN • ERR
DB	ADP3300ART-3.3	AD	reg	LDO; V _{IN} = 312 B; I _{DUT} = 50 mA; V _{DUT} = 3.3 B	SOT23-6	GND • NR • SD • OUT • IN • ERR
ΕB	ADP3300ART-5	AD	reg	LDO; V _{IN} = 312 B; I _{OUT} = 50 mA; V _{OUT} = 5 B	SOT23-6	GND • NR • SD • OUT • IN • ERR
LFB	ADP3300ART- 2.85	AD	reg	LDO; V _{IN} =312B; I _{OUT} =50mA; V _{OUT} =2.85B	SOT23-6	GND • NR • SD • OUT • IN • ERR
LTC	ADP3307ART-2.7	AD	reg	LDO; V _{IN} = 312 B; I _{DUT} = 100 mA; V _{DUT} = 2.7 B	SOT23-6	GND • NR • SD • OUT • IN • ERR
UC	ADP3307ART-3	AD	reg	LDO; V _{IN} = 312 B; I _{DUT} = 100 mA; V _{DUT} = 3 B	SOT23-6	GND • NR • SD • OUT • IN • ERR
VC.	ADP3307ART-3.2	AD	reg	LDO; V _{IN} = 312 B; I _{DUT} = 100 mA; V _{DUT} = 3.2 B	SOT23-6	GND • NR • SD • OUT • IN • ERR
WC	ADP3307ART-3.3	AD	reg	LDO; V _{IN} = 312 B; I _{DUT} = 100 mA; V _{DUT} = 3.3 B	SOT23-6	GND • NR • SD • OUT • IN • ERR
LXC	ADP3307ART- 2.85	AD	reg	LDO; V _{IN} =312B; I _{OUT} =100mA; V _{OUT} =2.85B	SOT23-6	GND • NR • SD • OUT • IN • ERR
M4	MBD110DW	ON	shd x2	$V_B < 7B$; $V_E (I_E = 10 \text{ mA}) < 0.6 \text{ B}$; $C_D < 1 \text{ n}\Phi$	SOT363, SC88	A1 • n. c. • K2 • A2 • n. c. • K1
MA	MBT3904DW1	ON	npn x2	$V_{CB0} = 60 \text{ B; } I_C = 200 \text{ mA; } P_D = 150 \text{ mBt; } h_{21} > 30; $ $f_T > 300 \text{ MFu}.$	SOT363, SC88	E2 • B2 • C1 • E1 • B1 • C2
MCs	BFS17S	SIEM	npn x2	$V_{CB0} = 25$ B; $I_C = 50$ mA; $P_D = 280$ mBT; $h_{21} = 20150$; $f_T > 2500$ MFU	SOT363, SC88	B1 • E1 • C2 • B2 • E2 • C1
MJ	MBT3904DW2	ON	npn x2	V_{CB0} = 60 B; I_C = 200 mA; P_D = 150 mBr; h_{21} > 30; f_T > 300 MFu	SOT363, SC88	B2 • B1 • C1 • E1 • E2 • C2
OMM	ADM8828ART	AD	dodo	$V_{IN} = 1.55.5 B$; $I_{OUT} > 25 \text{ MA}$; $V_{OUT} = -1.55.5 B$; $I_{CC} < 1 \text{ MA}$	SOT23-6	OUT • IN • CAP - • GND • SHDN • CAP+
MNO	ADM8829ART	AD	dodo	V_{IN} = 1.55.5 B; I_{DUT} > 25 MA; V_{DUT} = -1.55.5 B; I_{CC} < 1 MA	SOT23-6	OUT • IN • CAP - • GND • n. c. • CAP+
N06	DDC123JK	DIODS	Dnpn x2	$V_{CC} = 50 \text{ B; } I_C = 100 \text{ mA; } 2.2 \text{ k/}47 \text{ k}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
06V	DDC123JU	DIODS	Dnpn x2	$V_{CC} = 50 \text{ B; } I_C = 100 \text{ mA; } 2.2 \text{ k/}47 \text{ k}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
N07	DDC143TK	DIODS	Dnpn x2	$V_{CC} = 50 \text{ B; } I_C = 100 \text{ mA; } R_1 4.7 \text{ K}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
N07	DDC143TU		Dnpn x2	$V_{CC} = 50 \text{ B; } I_C = 100 \text{ mA; } R_1 4.7 \text{ K}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
N12	DDC114TK	DIODS	Dnpn x2	V _{DD} = 50 B; I _D = 100 mA; R ₁ 10 k	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1





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Код	Типономинал	5	Ф		Особенности		Корпус		1•2•3•4•5•6	ì
N12	DDC114TU	DIODS	Dnpn x2	V _{CC} =50E	3; I _C = 100 mA; R ₁ 10 k		SOT363, SC88	E1 • B1 • C	2•E2•B2•C1	ŀ
N13	DDC114EK	DIODS	Dnpn x2	V _{CC} =50E	3; I _C = 100 мА; 10 к/10 к		SOT23-6	E1 • B1 • C	2•E2•B2•C1	
N13	DDC114EU	DIODS	Dnpn x2	V _{CC} =50E	3; I _C = 100 mA; 10 k/10 k		SOT363, SC88	E1 • B1 • C	2•E2•B2•C1	
N14	DDC114YK	DIODS	Dnpn x2	V _{CC} =50E	3; I _C = 100 мА; 10 к/47 к		SOT23-6	E1 • B1 • C	2•E2•B2•C1	
N14	DDC114YU	DIODS	Dnpn x2	V _{CC} =50E	3; I _C = 100 mA; 10 k/47 k		SOT363, SC88	E1 • B1 • C	2•E2•B2•C1	
N17	DDC124EK	DIODS	Dnpn x2	V _{CC} =50E	3; I _C = 100 мА; 22 к/22 к		SOT23-6	E1 • B1 • C	2•E2•B2•C1	
N17	DDC124EU	DIODS	Dnpn x2	V _{CC} =50E	3; I _C = 100 mA; 22 k/22 k		SOT363, SC88	E1 • B1 • C	2•E2•B2•C1	Ĭ
N20	DDC144EK	DIODS	Dnpn x2	V _{CC} =50E	3; I _C = 100 мА; 47 к/47 к		SOT23-6	E1 • B1 • C	2 • E2 • B2 • C1	
N20	DDC144EU	DIODS	Dnpn x2	V _{CC} =50E	$I_C = 100 \text{ mA}; 47 \text{ k}/47 \text{ k}$		SOT363, SC88	E1 • B1 • C	2•E2•B2•C1	1
NN	HSMS282N	HP	shd x4		3; V _F (I _F = 30 мА) < 0.7 В; В) < 100 нА; С _Т < 1.0 пФ; В _С	₀ = 12 Ом	SOT363, SC88	K1 • A1, A2 A2, A3, A4 •	, A3, A4 • K2 • K • K4	3•A1,
nQ	μPA841TD	NEC	npn x2	V _{CB0} =9E f _{T1} >10ΓI	; I _{C1} = 30 мА; I _{C2} = 100 мА; I Гц; f _{T2} > 3.5 ГГц	P _D =210мВт;	M16, 1208	C1•E1•C	2 • B2 • E2 • B1	
0	HSMS280R	HP	shd x4		3; V _F (I _F =15мA) < 1.0 В; 0 В) < 200 нА; С ₀ < 2.0 пФ		SOT363, SC88	K1 • A1, K2	•A2 •K3 •A3,k	(4 • A4
00	HSMS282R	HP	shd x4		3; V _F (I _F = 30 мА) < 0.7 В; В) < 100 нА; С _Т < 1.0 пФ; Р _Г	= 120м	SOT363, SC88	K1 • A1, K2	•A2 •K3 •A3, I	K4•A4
P06	DDA123JK	DIODS	Dpnp x2	V _{CC} =50E	3; I _C = 100 mA; 2.2 k/47 k		SOT23-6	E1 • B1 • C	2•E2•B2•C1	7
P06	DDA123JU	DIODS	Dpnp x2	V _{CC} =50E	3; I _C = 100 mA; 2.2 k/47 k		SOT363, SC88	E1 • B1 • C	2•E2•B2•C1	
P07	DDA143TK	DIODS	Dpnp x2	V _{CC} =50E	3; I _C = 100 мА; R ₁ 4.7 к		SOT23-6	E1 • B1 • C	2•E2•B2•C1	
P07	DDA143TU	DIODS	Dpnp x2	V _{CC} =50E	$I_C = 100 \text{ mA}; R_1 4.7 \text{ K}$		SOT363, SC88	E1 • B1 • C	2•E2•B2•C1	3
P12	DDA114TK	DIODS	Dpnp x2	V _{CC} =50E	3; I _C = 100 mA; R ₁ 10 k		SOT23-6	E1 • B1 • C	2 • E2 • B2 • C1	
P12	DDA114TU	DIODS	Dpnp x2	V _{CC} =50E	B; I _C = 100 мА; R ₁ 10 к		SOT363, SC88	E1 • B1 • C	2•E2•B2•C1	
P13	DDA114EK	DIODS	Dpnp x2	00	3; I _C = 100 мA; 10 к/10 к				2•E2•B2•C1	
P13	DDA114EU	DIODS	Dpnp x2	V _{CC} =50E	3; I _C = 100 mA; 10 k/10 k		SOT363, SC88	E1 • B1 • C	2•E2•B2•C1	
P14	DDA114YK	DIODS	Dpnp x2	V _{CC} =50E	3; I _C = 100 mA; 10 k/47 k		SOT23-6	E1 • B1 • C	2 • E2 • B2 • C1	
P14	DDA114YU	DIODS	Dpnp x2	V _{CC} =50E	3; I _C = 100 mA; 10 k/47 k		SOT363, SC88	E1 • B1 • C	2•E2•B2•C1	
P17	DDC124EK	DIODS	Dpnp x2	V _{CC} =50E	3; I _C = 100 mA; 22 k/22 k		SOT23-6	E1 • B1 • C	2 • E2 • B2 • C1	
P17	DDC124EU	DIODS	Dpnp x2	V _{CC} =50E	3; I _C = 100 mA; 22 k/22 k		SOT363, SC88	E1 • B1 • C	2•E2•B2•C1	
P20	DDA144EK	DIODS	Dpnp x2		3; I _C = 100 мА; 47 к/47 к		SOT23-6	E1 • B1 • C	2•E2•B2•C1	Y
P20	DDA144EU	DIODS	Dpnp x2	V _{CC} =50E	3; I _C = 100 mA; 47 k/47 k		SOT363, SC88	E1 • B1 • C	2•E2•B2•C1	l .
PGs	BG4428	INF	amp	V _{CC} =2.4.	3B; I _{CC} = 8.2 mA; G _{MA} = 20) дБ (f _T = 1 ГГц)	SOT363, SC88	VD•GND•	OUT • GS • GNI	D•IN
PL	HSMS285L	HP	shd x3	V _E (I _E = 1 r	мA) < 0.25B; С _т = 0.3 пФ		SOT363, SC88	A1 • A2 • A3	3 • K3 • K2 • K1	
PP	HSMS285P	HP	shd x4	V _E (I _E = 1 a	лА) < 0.25B; С _т = 0.3 пФ		SOT363, SC88	A1 • K1, A2	•K2•K3•K4,	43 • A4
R10B	REG710NA-5	TI	scvcon	V _{IN} =1.8.	.5.5 В; I _{OUT} > 30 мА; V _{DUT} =	5.0 B	SOT23-6	VOUT • GNI VIN • CPUN	D • Enable • CPI IP+	JMP●
R10C	REG710NA-3.3	TI	scvcon	V _{IN} =1.8.	.5.5 В; I _{OUT} > 30 мА; V _{DUT} =	3.3B	SOT23-6	VOUT • GNI VIN • CPUN	D • Enable • CPI IP+	JMP •
R10D	REG710NA-3	TI	scvcon	V _{IN} =1.8.	.5.5 В; I _{OUT} > 30 мА; V _{OUT} =	3.0 B	SOT23-6	VOUT • GNI VIN • CPUN	D • Enable • CPU IP+	JMP•
R10F	REG710NA-2.7	TI	scvcon	V _{IN} = 1.8	.5.5 В; I _{OUT} > 30 мА; V _{OUT} =	2.7B	SOT23-6	VOUT • GNI VIN • CPUN	D • Enable • CPI IP+	JMP •



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
R10G	REG710NA-2.5	П	scvcon	V _{IN} = 1.85.5 B; I _{DUT} > 30 mA; V _{DUT} = 2.5 B	SOT23-6	VOUT • GND • Enable • CPUMP • VIN • CPUMP+
R10H	REG71055DDC	TI	scvcon	V _{IN} = 1.85.5 B; I _{DUT} > 30 mA; V _{DUT} = 5.5 B	TSOT23-	VCUT • GND • Enable • CPUMP • VIN • CPUMP+
R24	μPA801TFB	NEC	npn x2	$V_{CB0} = 20 \text{ B; } I_C = 100 \text{ mA; } P_D = 230 \text{ mBT; } h_{21} = 70140; f_T > 3 \Gamma \Gamma I_L$	SOT363, SC88	C1 • E1 • C2 • E2 • B2 • B1
R25	μPA801TGB	NEC	npn x2	$V_{CB0} = 20 \text{ B; } I_C = 100 \text{ mA; } P_D = 230 \text{ mBt; } h_{21} = 125250; f_T > 3 \Gamma \Gamma \mu$	SOT363, SC88	C1 • E1 • C2 • E2 • B2 • B1
R34	µPA802TFB	NEC	npn x2	$V_{CB0} = 20 \text{ B}; I_C = 65 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} = 70150; f_T > 4.5 \Gamma\Gamma U$	SOT363, SC88	C1 • E1 • C2 • E2 • B2 • B1
R35	μPA802TGB	NEC	npn x2	$V_{CB0} = 20 \text{ B; } I_C = 65 \text{ MA; } P_D = 200 \text{ MBT; } I_{21} = 110240; f_T > 4.5 \Gamma \Gamma_U$	SOT363, SC88	C1 • E1 • C2 • E2 • B2 • B1
R84	μPA827TF	NEC	npn x2	$V_{CB0} = 5 \text{ B; } I_C = 10 \text{ mA; } P_D = 60 \text{ mBr; } h_{21} = 70140; $ $f_T > 8.5 \Gamma \Gamma u$	TSOT36	C1 • E1 • C2 • B2 • E2 • B1
R86	μPA828TF	NEC	npn x2	$V_{CB0} = 5 \text{ B}; I_C = 30 \text{ mA}; P_D = 180 \text{ mB}\tau; h_{21} = 70140; f_T > 7 \Gamma \Gamma_U$	TSOT36	C1 • E1 • C2 • B2 • E2 • B1
REs	BFS480	SIEM	npn x2	V_{CBQ} = 10 B; IC = 10 mA; P_D = 80 mBT; h_{21} = 30200; f_T = 7500 MF $_{II}$	SOT363, SC88	B1 • E1 • C2 • B2 • E2 • C1
RFs	BFS481	SIEM	npn x2	$V_{CBQ} = 20 \text{ B; } I_C = 20 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} = 50200; $ $f_T = 8000 \text{ MF } q$	SOT363, SC88	B1 • E1 • C2 • B2 • E2 • C1
RGs	BFS482	SIEM	npn x2	V_{CB0} = 20 B; I_C = 35 mA; P_D = 250 mBT; h_{21} = 50200; f_T = 8000 MF $_{II}$	SOT363, SC88	B1 • E1 • C2 • B2 • E2 • C1
RHs	BFS483	SIEM	npn x2	$V_{CB0} = 20 \text{ B; } I_C = 65 \text{ mA; } P_D = 450 \text{ mBT; } h_{21} = 50200; \\ f_T = 8000 \text{ MF } u$	SOT363, SC88	B1 • E1 • C2 • B2 • E2 • C1
RL	μPA800T	NEC	npn x2	$V_{CB0} = 20 \text{ B; } I_C = 35 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} = 80200; $ $f_T > 5.5 \Gamma \Gamma u$	SOT363, SC88	C1 • E1 • C2 • E2 • B2 • B1
RL	µPA800TF	NEC	npn x2	$V_{CB0} = 20 \text{ B; } I_C = 35 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} = 80200; $ $f_T > 5.5 \Gamma \Gamma \text{U},$	TSOT36	C1 • E1 • C2 • E2 • B2 • B1
S00	ADG741BKSZ	AD	asw	2 x SPST; R _{DN} < 4 O _M ; V _{DD} = 1.85.5 B	SOT363, SC88	D • S • GND • IN • n. c. • VDD
S01	ADG742BKSZ	AD	asw	$2 \times SPST$; $R_{DN} < 4 \text{ OM}$; $V_{DD} = 1.85.5 \text{ B}$	SOT363, SC88	D • S • GND • IN • n. c. • VDD
SOM	ADG779BKSZ	AD	asw	SPDT; R _{ON} < 6 O _M ; V ₀₀ = 1.85.5B	SOT363, SC88	IN • VDD • GND • S1 • D • S2
S18	ADG602BRTZ	AD	asw	SPST; R _{DN} < 5.5 OM; V _{DD} = 2.75.5/±2.7±5.5 B	SOT23-6	VDD•S•VSS•GND•D•IN
s1A	SMBT3904S	SIEM	npn x2	$V_{CB0} = 60 \text{ B; } I_C = 200 \text{ mA; } P_D = 250 \text{ mBr; } I_{21} = 100300; f_T > 300 \text{MFu; }$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
s1A	SMBT3904U	SIEM	npn x2	$V_{CB0} = 60 \text{ B; } I_C = 200 \text{ mA; } P_D = 250 \text{ mBr; } I_{21} = 100300; f_T > 300 \text{MFu},$	SOT457, SC74	E1 • B1 • C2 • E2 • B2 • C1
S1B	ADG465BRT	AD	prot	V _{PRDT} < ±40B; V _{DD} =±15B	SOT23-6	VD1 • n. c. • VSS • VS1 • n. c. • VD0
s2A	SMBT3906S	SIEM	рпр х2	$V_{CB0} = 40 \text{ B; } I_C = 200 \text{ mA; } P_D = 250 \text{ mBr; } I_{21} = 100300; f_T > 250 \text{MFц}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
s2A	SMBT3906U	SIEM	pnp x2	$V_{CB0} = 40 \text{ B}; I_C = 200 \text{ mA}; P_D = 250 \text{ mBr}; h_{21} = 100300; f_T > 250 \text{ MFu}$	SOT457, SC74	E1 • B1 • C2 • E2 • B2 • C1
S3B	ADG701BRT	AD	asw	SPST; R _{DN} <40m; V _{DB} =1.85.5B	SOT23-6	D • S • GND • IN • n. c. • VDD
s3P	SMBT3904PN	SIEM	npn/pnp	V_{CB0} = 40 B; I_C = 200 mA; P_D = 250 mBt; h_{21} = 100300; f_T > 250 MFu	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
S4B	ADG702BRT	AD	asw	SPST; R _{DN} < 4 Om; V _{DD} = 1.85.5 B	SOT23-6	D • S • GND • IN • n. c. • VDD
S5B	ADG719BRT	AD	asw	SPDT; R _{ON} < 7 O _M ; V _{DD} = 1.85.5B	SOT23-6	IN • VDD • GND • S1 • D • S2
SDA	ADG751ART	AD	asw	SPST; R _{DN} < 40 O _M ; V _{DO} = 1.85.5 B	SOT23-6	S • VDD • n. c. • IN • GND • D
SDB	ADG751BRT	AD	asw	SPST; R _{DN} < 40 Om; V _{DO} = 1.85.5 B	SOT23-6	S • VDD • n. c. • IN • GND • D
SEB	ADG752BRT	AD	asw	SPDT; R _{ON} < 20 O _M ; V _{DD} = 1.85.5B	SOT23-6	D • VDD • S1 • IN • GND • S2
SFB	ADG741BKS	AD	asw	2 x SPST; R _{DN} < 4 OM; V _{DD} = 1.85.5 B	SOT363, SC88	D • S • GND • IN • n. c. • VDD
SGB	ADG742BKS	AD	asw	2 x SPST; R _{DN} < 4 O _M ; V _{DD} = 1.85.5 B	SOT363, SC88	D • S • GND • IN • n. c. • VDD





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
SHB	ADG749BKS	AD	asw .	SPDT; R _{DN} < 70 _M ; V _{DD} = 1.85.5 B	SOT363, SC88	IN • VDD • GND • S1 • D • S2
SKB	ADG779BKS	AD	asw .	SPDT; R _{ON} < 6 O _M ; V _{DO} = 1.85.5 B	SOT363, SC88	IN • VDD • GND • S1 • D • S2
SLB	ADG801BRT	AD	asw	SPST; R _{ON} < 0.40m; V _{DD} = 1.85.5B	SOT23-6	D • S • GND • IN • n. c. • VDD
SMB	ADG802BRT	AD	asw	SPST; R _{ON} < 0.40m; V _{DD} = 1.85.5B	SOT23-6	D • S • GND • IN • n. c. • VDD
SNB	ADG8 19BRT	AD	asw	SPDT; R _{ON} < 0.8 Om; V _{DO} = 1.85.5 B	SOT23-6	IN • VDD • GND • S1 • D • S2
SPB	ADG820BRT	AD	asw	SPDT; R _{DN} < 0.8 O _M ; V _{DD} = 1.85.5 B	SOT23-6	IN • VDD • GND • S1 • D • S2
STB	ADG601BRT	AD	asw	SPST; R _{ON} < 5.50m; V _{DO} = 2.75.5/±2.7±5.5B	SOT23-6	VDD • S • VSS • GND • D • IN
STB#	ADG601BRTZ	AD	asw	SPST; R _{ON} < 5.50M; V _{DD} = 2.75.5/±2.7±5.5B	SOT23-6	VDD • S • VSS • GND • D • IN
SUB	ADG602BRT	AD	asw	SPST; R _{ON} < 5.50m; V _{DO} = 2.75.5/±2.7±5.5B	SOT23-6	VDD • S • VSS • GND • D • IN
T1	EMT1	ROHM	pnp x2	$V_{CBD} = 60 \text{ B; } I_C = 150 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} > 120$	SOT563, EMT6	E1 • B1 • C2 • E2 • B2 • C1
T1	IMT1A	ROHM	pnp x2	$V_{CBD} = 60 \text{ B}; I_C = 150 \text{ mA}; P_D = 300 \text{ mB}T; h_{21} > 120$	SOT23-6	C1•B1•E2•C2 •B1•E1
T1	UMT1N	ROHM	pnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D (com.) = 300 \text{ mBT}; h_{21} > 120$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
T17	IMT17	ROHM	pnp x2	V _{CBD} = 60 B; I _C = 500 mA; P _D = 300 mBT; h ₂₁ > 120	SOT23-6	C1 • B2 • E2 • C2 • B1 • E1
T1H	ADT7301ARTZ	AD	dts	13-pasp.; SPI/QSPI/Microwire; V ₀₀ =2.75.25B	SOT23-6	GND • DIN • VDD • SCLK • CS • DOUT
T2	EMT2	ROHM	рпр х2	$V_{CBD} = 60 \text{ B; } I_C = 150 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} > 100$	SOT563, EMT6	E2 • E1 • B1 • C1 • B2 • C2
T2	IMT2A	ROHM	pnp x2	$V_{CBD} = 60 \text{ B}; I_C = 150 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 100$	SOT23-6	C2 • B2 • C1 • B1 • E1 • E2
T2	UMT2N	ROHM	pnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D (com.) = 300 \text{ mBT}; h_{21} > 120$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
T3	EMT3	ROHM	рпр х2	V _{CBO} = 60 B; I _C = 150 mA; P _D = 150 mBr; h ₂₁ > 100	SOT563, EMT6	E2 • B2 • B1 • C1 • E1 • C2
T3	IMT3A	ROHM	pnp x2	V _{CBD} = 60 B; I _C = 150 мА; P _D = 300 мВт; h ₂₁ > 100	SOT457, SC74	C2 • E1 • C1 • B1 • B2 • E2
T3	UMT3N	ROHM	рпр х2	V _{CBD} =50 B; I _C =100 mA; P _D (com.)=300 mBr; In ₂₁ >120	SOT363, SC88	E1 • B1 • B2 • C2 • E2 • C1
T4	IMT4	ROHM	pnp x2	$V_{CBD} = 120 \text{ B}; I_C = 50 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 180$	SOT23-6	C1 • E2 • C2 • B2 • B1 • E1
T4	MBD330DW	ON	shd x2	$V_R < 30 \text{ B}; V_F (I_F = 10 \text{ mA}) < 0.6 \text{ B}; C_D < 1 \text{ n}\Phi$	SOT363, SC88	A1 • n. c. • K2 • A2 • n. c. • K1
T76	µPA804TFB	NEC	npn x2	V_{DB0} =20 B; I_{C} =60 mA; P_{D} =200 mBr; h_{21} =60120; f_{T} >3 $\Gamma \Gamma u_{c}$	SOT363, SC88	C1 • E1 • C2 • E2 • B2 • B1
T77	µPA804TGB	NEC	npn x2	$V_{CB0} = 20 \text{ B}; I_C = 60 \text{ mA}; P_D = 200 \text{ mBT}; h_{21} = 100200; f_T > 3 \Gamma \Gamma \mu$	SOT363, SC88	C1 • E1 • C2 • E2 • B2 • B1
T83	µРА806Т	NEC	npn x2	$V_{CB0} = 9 \text{ B; } I_C = 30 \text{ mA; } P_D = 200 \text{ mBt; } h_{21} = 75150; $ $f_T = 12 \Gamma \Gamma I_L$	SOT363, SC88	C1 • E1 • C2 • E2 • B2 • B1
T84	μPA807T	NEC	npn x2	$V_{CB0} = 5 \text{ B; } I_C = 10 \text{ mA; } P_D = 60 \text{ mBr; } h_{21} = 70140; $ $f_T > 8.5 \Gamma \Gamma \mu$	SOT363, SC88	C1•E1•C2•E2•B2•B1
T86	μPA808T	NEC	npn x2	$V_{CB0} = 5 B; I_C = 30 \text{ mA}; P_D = 180 \text{ mB} \text{ r}; h_{21} = 70140; f_T > 7 \Gamma \Gamma I,$	SOT363, SC88	C1 • E1 • C2 • E2 • B2 • B1
TCA	ADT7301ART	AD	dts	13-pasp.; SPI/QSPI/Microwire; V _{DO} =2.75.25B	SOT23-6	GND • DIN • VDD • SCLK • CS • DOUT
TK	HSMS286K	HP	shd x2	V _F (I _F =1 мA) < 0.35B; C _T < 0.30 пФ	SOT363, SC88	A1 • n. c. • A2 • K2 • n. c. • K1
TL	HSMS286L	HP	shd x3	$V_F(I_F = 1 \text{ MA}) \le 0.35 \text{ B}; C_T \le 0.30 \text{ n}\Phi$	SOT363, SC88	A1 • A2 • A3 • K3 • K2 • K1
TOH	AD7414ARTZ	AD	dts	10-pasp.; SMBus/I ² C; V ₀₀ =2.75.5 B	SOT23-6	AS • GND • VDD • SCL • ALERT • SDA
TQJ	AD7414ARTZ	AD	dts	10-pasp.; SMBus/I ² C; V _{DD} =2.75.5 B	SOT23-6	AS • GND • VDD • SCL • ALERT • SDA
TOK	AD7414ARTZ	AD	dts	10-pasp.; SMBus/I ² C; V ₀₀ =2.75.5 B	SOT23-6	AS • GND • VDD • SCL • ALERT • SDA
TP	HSMS286P	HP	shd x4	V _E (I _E = 1 мА) < 0.35 В; С _Т < 0.30 пФ	SOT363, SC88	A1 • K1, A2 • K2 • K3 • K4, A3 • A4



Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
TR	HSMS286R	HP	shd x4	$V_F(I_F = 1 \text{ mA}) < 0.35 \text{ B}; C_T < 0.30 \text{ n}\Phi$	SOT363, SC88	K1 • A1, K2 • A2 • K3 • A3, K4 • A4
VΑ	RN4601	TOSH	Dpnp/npn	$V_{CB0} = 50 B_1 I_C = 100 \text{mA}, P_D = 300 \text{mB}$; $f_T = 200 \text{MFu}, R_1/R_2 = 4.7 \text{KOm}/4.7 \text{KOm}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
VΑ	RN4901	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 4.7 \text{ KOm}/4.7 \text{ KOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
VΑ	RN4901FE	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{B;} I_C = 100 \text{mA;} P_D = 100 \text{mBT;} f_T = 200 \text{МГц;} P_{1/} P_{2} = 4.7 \text{кOm}/4.7 \text{кOm}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
IYAV	TLV2630IDBV	TI	OA	R-R; V _{DD} = 2.75.5 B; f _{BD} = 9MFu; V _{DSI} < 4.5 mB		OUT • GND • IN + • IN • SHDN • VDD
VΒ	RN4602	TOSH	Dpnp/npn	$V_{CB0} = 50 B_1 I_C = 100 \text{мA}; P_D = 300 \text{мBT}; f_T = 200 \text{МГц}; R_1/R_2 = 10 \text{кОм}/10 \text{кОм}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
VΒ	RN4902	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 10 \text{ kOm}/10 \text{ kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
VΒ	RN4902FE	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 10 \text{ kOm}/10 \text{ kOm}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
VC	RN4603	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 22 \text{ KOm}/22 \text{ KOm}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
VC	RN4903	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBt; } f_T = 200 \text{ MFu; } R_1/R_2 = 22 \text{ kOm}/22 \text{ kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
VC	RN4903FE	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 22 \text{ kOm/}22 \text{ kOm}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
VD	RN4604	TOSH	Dpnp/npn	$V_{CB0} = 50 B; I_C = 100 \text{mA}; P_D = 300 \text{mBT}; f_T = 200 \text{MFu}; R_1/R_2 = 47 \kappa O m/47 \kappa O m$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
VD.	RN4904	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 47 \text{ kOm}/47 \text{ kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
VD.	RN4904FE	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 100 \text{ mBT}; f_T = 200 \text{ MFu}; R_1/R_2 = 47 \text{ kOm}/47 \text{ kOm}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
VΕ	RN4605	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{B;} I_C = 100 \text{mA;} P_D = 300 \text{mBT;} f_T = 200 \text{MFu;} R_1/R_2 = 2.2 \text{KOm}/47 \text{KOM}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
VΕ	RN4905	TOSH	Dpnp/npn	$V_{DB0} = 50 B_1 I_C = 100 \text{mA}, P_D = 200 \text{mBT}, f_T = 200 \text{MFu}, R_1/R_2 = 2.2 \text{KOm}/47 \text{KOM}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
VΕ	RN4905FE	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 2.2 \text{ kOm}/47 \text{ kOm}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
VF	RN4606	TOSH	Dpnp/npn	V_{CB0} = 50 B; I_C = 100 мА; P_D = 300 мВт; f_T = 200 МГц; R_1/R_2 = 4.7 кОм/47 кОм	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
VF	RN4906	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBr; } f_T = 200 \text{ MFu; } R_1/R_2 = 4.7 \text{ kOm}/47 \text{ kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
VF.	RN4906FE	TOSH	Dpnp/npn	$V_{CB0} = 50 B_1^* I_C = 100 \text{mA}, P_D = 100 \text{mBT}, f_T = 200 \text{MFu}, R_1/R_2 = 4.7 \text{KOm}/47 \text{KOM}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
Ή	µPA851TD	NEC	npn x2	$V_{CB01} = 5 B$; $V_{CB02} = 15 B$; $I_{C1} = 30 \text{ mA}$; $I_{C2} = 100 \text{ mA}$; $P_D = 210 \text{ mBT}$; $f_{T1} > 10 \Gamma \Gamma \mu$; $f_{T2} > 4.5 \Gamma \Gamma \mu$	M16, 1208	C1 • E1 • C2 • B2 • E2 • B1
VH	RN4607	TOSH	Dpnp/npn	$V_{CB0} = 50 B; I_C = 100 \text{mA}; P_D = 300 \text{mBT}; f_T = 200 \text{MFu}; R_1/R_2 = 10 \text{KOm}/47 \text{KOM}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
VH	RN4907	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 10 \text{ kOm}/47 \text{ kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
VΗ	RN4907FE	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{B;} I_C = 100 \text{mA;} P_D = 100 \text{mBT;} f_T = 200 \text{MFu;} R_1/R_2 = 10 \text{KOm}/47 \text{KOM}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
VI.	RN4608	TOSH	Dpnp/npn	$V_{CB0} = 50 B; I_C = 100 \text{mA}; P_D = 300 \text{mBT}; f_T = 200 \text{MFL}; R_1/R_2 = 22 \kappa O m/47 \kappa O m$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
VI	RN4908	TOSH	Dpnp/npn	V _{CB0} = 50 B; I _C = 100 мА; P _D = 200 мВт; f _T = 200 МГц; R ₁ /R ₂ = 22 кОм/47 кОм	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
VI	RN4908FE	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 22 \text{ KOm}/47 \text{ KOM}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
W	RN4609	TOSH	Dpnp/npn	(a) (b)	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
W.	RN4909	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBt; } f_T = 200 \text{ MFu; } R_1/R_2 = 47 \text{ KOm}/22 \text{ KOM}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1



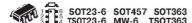


Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
IJ	RN4909FE	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 47 \text{ kOm}/22 \text{ kOm}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
√K	RN4610	TOSH	Dpnp/npn	V_{CB0} = 50 B; I_C = 100 mA; P_D = 300 mBτ; f_T = 200 MΓц; P_1 = 4.7 κOm	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
VK	RN4910	TOSH	Dpnp/npn	V_{CB0} = 50 B; I_C = 100 мA; P_D = 200 мВт; f_T = 200 МГц; R_1 = 4.7 кОм	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
VK	RN4910FE	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1 = 4.7 \text{ kOm}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
٧L	µPA854TD	NEC	npn x2	$V_{CB01} = 9 B$; $V_{CB02} = 15 B$; $I_{C1} = 30 \text{ mA}$; $I_{C2} = 100 \text{ mA}$; $P_D = 210 \text{ mBT}$; $f_{T1} > 10 \Gamma \Gamma \mu$; $f_{T2} > 3 \Gamma \Gamma \mu$	M16, 1208	C1 • E1 • C2 • B2 • E2 • B1
/M	RN4611	TOSH	Dpnp/npn	V_{CB0} = 50 B; I_C = 100 mA; P_D = 300 mB τ ; f_T = 200 M Γ u; R_1 = 10 kOm	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
VM	RN4911	TOSH	Dpnp/npn	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; f_T = 200 MFu; R_1 = 10 kOm	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
VM	RN4911FE	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1 = 10 \text{ kOm}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
νN	μPA855TD	NEC	npn x2	$V_{CB01} = 5 B$; $V_{CB02} = 15 B$; $I_{C1} = 30 \text{ mA}$; $I_{C2} = 100 \text{ mA}$; $P_0 = 210 \text{ mB}$; $f_{T1} > 10 \Gamma \Gamma u$; $f_{T2} > 3 \Gamma \Gamma u$	M16, 1208	C1 • E1 • C2 • B2 • E2 • B1
VN	RN4612	TOSH	Dpnp/npn	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBT; } f_T = 200 \text{ MFu; } R_1 = 22 \text{ KOM}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
νT	µPA859TD	NEC	npn x2	$V_{CB01} = 5 \text{ B}; V_{CB02} = 9 \text{ B}; I_{C1} = 30 \text{ mA}; I_{C2} = 100 \text{ mA}; P_D = 210 \text{ mBr}; f_{T1} > 10 \Gamma \Gamma \mu; f_{T2} > 4 \Gamma \Gamma \mu$	M16, 1208	C1 • E1 • C2 • B2 • E2 • B1
νV	μPA860TD	NEC	npn x2	$V_{CB01} = 9 \text{ B}; V_{CB02} = 9 \text{ B}; I_{C1} = 30 \text{ mA}; I_{C2} = 35 \text{ mA}; P_D = 210 \text{ mBr}; f_{T1} > 10 \Gamma \Gamma \mu; f_{T2} > 17 \Gamma \Gamma \mu$	M16, 1208	C1•E1•C2•B2•E2•B1
νX	μPA861TD	NEC	npn x2	$V_{CB01} = 5 \text{ B}; V_{CB02} = 9 \text{ B}; I_{C1} = 30 \text{ mA}; I_{C2} = 35 \text{ mA}; P_D = 195 \text{ mBr}; f_{T1} > 10 \Gamma \Gamma \text{ U}; f_{T2} > 17 \Gamma \text{ TU}$	M16, 1208	C1 • E1 • C2 • B2 • E2 • B1
νY	µPA862TD	NEC	npn x2	$V_{CB01} = 9B$; $V_{CB02} = 9B$; $I_{C1} = 30$ mA; $I_{C2} = 100$ mA; $P_D = 210$ mBr; $f_{T1} > 10$ ГГЦ; $f_{T2} > 3$ ГГЦ	M16, 1208	C1 • E1 • C2 • B2 • E2 • B1
νY	μPA862TS	NEC	npn x2	$V_{CB01} = 9 \text{ B}; V_{CB02} = 9 \text{ B}; I_{C1} = 30 \text{ mA}; I_{C2} = 100 \text{ mA}; P_0 = 130 \text{ mBr}; f_{T1} > 10 \Gamma \Gamma \mu; f_{T2} > 3 \Gamma \Gamma \mu$	SOT666	C1•E1•C2•B2•E2•B1
W10	FMW10	ROHM	npn x2	V_{CB0} =30 B; I_C =50 mA; P_D =300 mBT; h_{21} >27	SOT23-6	C1 • C2 • B2 • E1, E2 • B1 • n. c.
W10	UMW10N	ROHM	npn x2	V_{CB0} =30 B; I_C =50 mA; P_D (com.) =300 mBr; I_{CB1} =27270; I_T >1500 MFų	SOT363, SC88	B1 • E1, E2 • B2 • C2 • C1 • n. c.
W1s	BCR10PN	INF	Dpnp(2) +npn(1)	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBT; } h_{21} > 30; $ $f_T = 130 \text{ MFu}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
W5	SEMB10	INF	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 70 \text{ mA; } P_D = 250 \text{ mBT; } h_{21} > 70; $ $f_T = 100 \text{ MFu}$	SOT666	E1 • B1 • C1 • E2 • B2 • C2
W8	FMW8	ROHM	npn x2	$V_{CB0} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D = 300 \text{ mBr; } h_{21} > 27$	SOT457, SC74	C1 • n. c. • C2 • B2 • E1, E2 • B1
WC	SEMH11	INF	Dpnp x2	$V_{CB0} = 50 \text{ B}, I_C = 100 \text{ mA}, P_D = 200 \text{ mBT}, h_{21} > 30, f_T = 130 \text{ MFц}$	SOT666	E1 • B1 • C1 • E2 • B2 • C2
WCs	BCR133S	INF	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 30; $ $f_T = 130 \text{ MFu}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
WCs	BCR133U	INF	Dpnp x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 200 mBT; h_{21} > 30; f_T = 130 MF $_{\rm H}$	SOT457, SC74	E1 • B1 • C1 • E2 • B2 • C2
WD	SEMH1	INF	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 50; $ $f_T > 130 \text{ MFL}$	SOT666	E1 • B1 • C1 • E2 • B2 • C2
WDs	BCR141S	INF	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBT; } h_{21} > 50; $ $f_T > 130 \text{ MFL}$	SOT363, SC88	E1 • B1 • C1 • E2 • B2 • C2
WDs	BCR141U	INF	Dpnp x2	V_{CB0} =50 B; I_C =100 mA; P_D =200 mBT; h_{21} >50; f_T >130 M Γ_{LL}	SOT457, SC74	E1 • B1 • C1 • E2 • B2 • C2
WE	SEMH2	INF	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 70 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 70; \\ f_T > 100 \text{ M} \Gamma_U$	SOT666	E1 • B1 • C1 • E2 • B2 • C2
WEs	BCR148S	INF	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 70 \text{ mA; } P_D = 250 \text{ mBT; } h_{21} > 70; \\ f_T > 100 \text{MFu}$	SOT363, SC88	E1 • B1 • C1 • E2 • B2 • C2
WEs	BCR148U	INF	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 70 \text{ mA; } P_D = 200 \text{ mBT; } h_{21} > 70;$ $f_T > 100 \text{ MFu}$	SOT457, SC74	E1 • B1 • C1 • E2 • B2 • C2





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
WFs	BCR08PN	INF	Dpnp(2) +npn(1)	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBt; } h_{21} > 70; $ $f_T = 170 \text{ MF}_H$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
WH	SEMH10	INF	Dрпр x2	V_{DB0} = 50 B; I_C = 100 мА; P_D = 200 мВт; h_{21} > 70; f_T > 170 МГц	SOT666	E1•B1•C1•E2•B2•C2
WHs	BCR108S	INF	Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; h_{21} > 70; f_T > 170 mFu	SOT363, SC88	E1 • B1 • C1 • E2 • B2 • C2
WJ	SEMH9	INF	Dpпр x2	V_{CB0} = 50 B; I_C = 100 мA; P_D = 250 мВт; h_{21} > 70; f_T > 150 МГц	SOT666	E1 • B1 • C1 • E2 • B2 • C2
WJs	BCR135S	INF	Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 250 mBT; h_{21} > 70; f_T > 150 MF $_{\rm H}$	SOT363, SC88	E1 • B1 • C1 • E2 • B2 • C2
WKs	BCR119S	INF	Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 250 mBT; I_{D1} = 120630; I_T > 150 M Γ_{II}	SC88	E1 • B1 • C1 • E2 • B2 • C2
WMs	BCR183S	INF	Dpnp x2	$V_{C80} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBt; } h_{21} > 30;$	SOT363, SC88	E1 •B1 •C2 •E2 •B2 •C1
WMs	BCR183U	INF	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBt; } h_{21} > 30;$	SOT457, SC74	E1 •B1 •C2 •E2 •B2 •C1
WNs	BCR185S	INF	Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 250 mBT; h_{21} > 70; f_T > 200 mFu	SC88	E1 •B1 •C1 •E2 •B2 •C2
WNs	BCR185U	INF	Дрпр х2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 250 mBT; h_{21} > 70; f_T > 200 mF $_{\rm L}$	SC74	E1 •B1 •C1 •E2 •B2 •C2
WOs	BCR191S	INF	Dpnp x2	V_{DB0} = 50 B; I_C = 100 mA; P_D = 250 mBr; h_{21} > 50; f_T > 200 mFu	SOT363, SC88	E1 •B1 •C1 •E2 •B2 •C2
WPs	BCR192U	INF	D pпр x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBt; } h_{21} > 70; \\ f_T > 200 \text{ MF}_{LL}$	SOT457, SC74	E1 •B1 •C1 •E2 •B2 •C2
WPs	BCR22PN	INF	Dpnp(2) +npn(1)	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBr; } h_{21} > 50; $ $f_T = 130 \text{ MFu}$	SOT363, SC88	E1 •B1 •C2 •E2 •B2 •C1
WRs	BCR198S	INF	D2 pnp x2	$V_{CB0} = 50 \text{ B; } I_C = 70 \text{ mA; } P_D = 250 \text{ mBT; } h_{21} > 70; \\ f_T > 190 \text{ MF}_{LL}$	SOT363, SC88	E1 •B1 •C1 •E2 •B2 •C2
WSs	BCR169S	INF	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBr; } h_{21} = 120630; f_T > 150 \text{MFu}$	SOT363, SC88	E1 •B1 •C1 •E2 •B2 •C2
WTs	BCR48PN	INF	Dpnp(1) +npn(2)	$V_{CB0} = 50 \text{ B}$; ICNPN = 70 mA ; ICPNP = 100 mA ; $P_D = 250 \text{ mB}$ T; $h_{21} > 70$; $f_T > 100 \text{ MF}$ ц	SOT363, SC88	E1 •B1 •C1 •E2 •B2 •C2
WU	MRF2947AT1	MOT	npn x2	$V_{CB0} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D = 188 \text{ mBT; } h_{21} = 75150; $ $f_T = 9 \Gamma \Gamma U_L$	SOT363, SC88	B1 • E2 • C2 • B2 • E1 • C1
WVs	BCR129S	INF	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBr; } h_{21} = 120630; f_T > 150 \text{MFu}$	SOT363, SC88	E1 • B1 • C1 • E2 • B2 • C2
WVs	BCR35PN	INF	Dpnp(1) +npn(2)	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 250 \text{ mBt; } h_{21} > 70; \\ f_T > 150 \text{ MFu,}$	SOT363, SC88	E1 • B1 • C1 • E2 • B2 • C2
X1	EMX1	ROHM	npn x2	$V_{CBD} = 60 \text{ B; } I_C = 500 \text{ mA; } P_D = 150 \text{ mBT; } h_{21} > 120$	SOT563, EMT6	E1•B1•C2 •E2•B2•C1
X 1	IMX1	ROHM	npn x2	V _{CBD} =60 B; I _C =150 мА; P _D =300 мВт; h ₂₁ >120	SOT23-6	C1 • B2 • E2 • C2 • B1 • E1
X1	UMX1N	ROHM	npn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D (\text{com.}) = 300 \text{ mBT; } I_{21} > 120$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
X11	UMX11N	ROHM	npn x2	$V_{CB0} = 25 \text{ B; } I_C = 20 \text{ mA; } h_{21} = 39180; f_T > 700 \text{ MF}_{\text{LL}}$	SOT363, SC88	E1 •B1 •B2 • C2 • E2 • C1
X17	IMX17	ROHM	npn x2	V _{CBD} = 60 B; I _C = 150 мА, P _D = 150 мВт; h ₂₁ > 120	SOT23-6	C1 • B2 • E2 • C2 • B1 • E1
Х2	IMX2	ROHM	npn x2	$V_{CB0} = 60 \text{ B; } I_C = 150 \text{ mA; } P_D = 300 \text{ mBt; } h_{21} > 120$	SOT23-6	C1 • B1 • C2 • B2 • E2 • E1
X2	UMX2N	ROHM	npn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D(\text{com.}) = 300 \text{ mBr;} \\ h_{21} > 120$	SOT363, SC88	E1 •E2 •B2 •C2 •B1 •C1
ХЗ	IMX3	ROHM	npn x2	$V_{CB0} = 60 \text{ B}; I_C = 150 \text{ mA}; P_D = 300 \text{ mBr}; h_{21} > 120$	SOT23-6	C1 • E2 • C2 • B2 • B1 • E1
Х3	UMX3N	ROHM	npn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D(\text{com.}) = 300 \text{ mBr;} \\ h_{21} > 120$	SOT363, SC88	E1 •B1 •B2 • C2 • E2 • C1
X4	EMX4	ROHM	npn x2	$V_{CB0} = 30 \text{ B; } I_C = 50 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} > 27$	SOT563, EMT6	E1•B1•B2 •C2•E2•C1
Χ4	IMX4	ROHM	npn x2	$V_{CB0} = 30 \text{ B}; I_C = 50 \text{ mA}; P_D = 300 \text{ mB}_T; h_{21} > 27$	SOT23-6	C1 • E2 • C2 • B2 • B1 • E1
X4	UMX4N	ROHM	npn x2	$V_{CB0} = 30 \text{ B; } I_C = 50 \text{ mA; } P_D (\text{com.}) = 300 \text{ mBT; } h_{21} = 56180; f_T > 1500 \text{ MFu}$	SOT363, SC88	E1 •B1 •B2 • C2 • E2 • C1



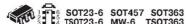


Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
(5	IMX5	ROHM	npn x2	V _{CB0} = 20 B; I _C = 50 мА; P _D = 300 мВт; h ₂₁ > 27	SOT23-6	C1 • E2 • C2 • B2 • B1 • E1
X 5	UMX5N	ROHM	npn x2	V_{CB0} = 30 B; I_C = 50 mA; P_D (com.) = 300 mBT; I_{D1} = 56180; I_T > 1500 MF I_T	SOT363, SC88	E1 •B1•B2•C2•E2•C1
X6	UMX6N	ROHM	npn x2	V_{CB0} =40 B; I_C =50 мA; P_D (com.)=300 мBт; I_{D1} >56; I_T >300 МГц	SOT363, SC88	E1 •E2•B2•C2•B1•C1
X8	IMX8	ROHM	npn x2	$V_{CB0} = 120 \text{ B}; I_C = 50 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 180$	SOT23-6	C1 • E2 • C2 • B2 • B1 • E1
X9	IMX9	ROHM	npn x2	$V_{CB0} = 25 \text{ B}; I_C = 500 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 560$	SOT23-6	C1 • B2 • E2 • C2 • B1 • E1
XA	RN1601	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 4.7 \text{ kOm}/4.7 \text{ kOm}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
XA	RN1901	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; f_T = 250 MFu; R_1/R_2 = 4.7 kOm/4.7 kOm	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
XΑ	RN1901FE	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 100 mBT; f_T = 250 MFu; R_1/R_2 = 4.7 kOm/4.7 kOm		
XB	RN1602	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 300 mBT; f_T = 250 MFu; R_1/R_2 = 10 kOm/10 kOm		
XB	RN1902	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 мА; P_D = 200 мВт; f_T = 250 МГц; R_1/R_2 = 10 кОм/10 кОм	SC88	
XB	RN1902FE	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 100 mBT; f_T = 250 MFu; P_1/P_2 = 10 kOm/10 kOm	SOT666	
хC	µPA863TD	NEC	npn x2	$V_{CB01} = 5 B$; $V_{CB02} = 9 B$; $I_{C1} = 30 \text{ mA}$; $I_{C2} = 100 \text{ mA}$; $P_D = 130 \text{ mB} \tau$; $f_{T1} > 10 \Gamma \Gamma \mu$; $f_{T2} > 3 \Gamma \Gamma \mu$	M16, 1208	C1 • E1 • C2 • B2 • E2 • B1
кC	µPA863TS	NEC	npn x2	$V_{CB01} = 5 B$; $V_{CB02} = 9 B$; $I_{C1} = 30 \text{ mA}$; $I_{C2} = 100 \text{ mA}$; $P_0 = 130 \text{ mB}$ T; $f_{T1} > 10 \Gamma \Gamma u$; $f_{T2} > 3 \Gamma \Gamma u$	SOT666	C1 • E1 • C2 • B2 • E2 • B1
XC	RN1603	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 300 mBT; f_T = 250 M Γ_L I; R_1/R_2 = 22 kOm/22 kOm	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
XC	RN1903	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mB} \tau; f_T = 250 \text{ MFu; } R_1/R_2 = 22 \text{ kOm}/22 \text{ kOm}$	SC88	
XC	RN1903FE	TOSH	Dnpn x2	V_{CBO} = 50 B; I_C = 100 mA; P_D = 100 mBT; f_T = 250 MFu; R_1/R_2 = 22 kOm/22 kOm		
XD	RN1604	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 300 \text{ mBT}; f_T = 250 \text{ MFu}; R_1/R_2 = 47 \text{ kOm}/47 \text{ kOm}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
XD	RN1904	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; f_T = 250 MFu; R_1/R_2 = 47 kOm/47 kOm	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
XD	RN1904FE	TOSH	Dnpn x2	$V_{CB0} = 50$ B; $I_C = 100$ mA; $P_D = 100$ mBT; $f_T = 250$ MFL; $R_1/R_2 = 47$ κOm/47 κOm		
XE	RN1605	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 300 mBT; f_T = 250 MFu; R_1/R_2 = 2.2 kOm/47 kOm		
XE	RN1905	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; f_T = 250 MFu; R_1/R_2 = 2.2 kOm/47 kOm	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
XE	RN1905FE	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 100 mBT; f_T = 250 MFu; R_1/R_2 = 2.2 kOm/47 kOm		
XF	RN1606	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 300 mBT; f_T = 250 MFu; R_1/R_2 = 4.7 kOm/47 kOm		
XF	RN1906	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; f_T = 250 MFu; R_1/R_2 = 4.7 kOm/47 kOm	SC88	
XF	RN1906FE	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 100 mBT; f_T = 250 MFu; R_1/R_2 = 4.7 kOm/47 kOm	SOT666	E1 • B1 • C2 • E2 • B2 • C1
XH	RN1607	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 300 mB t; f_T = 250 MFu; R_1/R_2 = 10 kOm/47 kOm		
XH	RN1907	TOSH	Dnpn x2	V_{CBO} = 50 B; I_C = 100 мА; P_D = 200 мВт; f_T = 250 МГц; R_1/R_2 = 10 кОм/47 кОм	SC88	
XH	RN1907FE	TOSH	Dnpn x2	V_{CBD} = 50 B; I_C = 100 mA; P_D = 100 mBT; f_T = 250 MFu; P_1/P_2 = 10 kOm/47 kOm		**************************************
XI XI	RN1608	TOSH	Dnpn x2	V_{CBD} = 50 B; I_C = 100 мА; P_D = 300 мВт; f_T = 250 МГц; R_1/R_2 = 22 кОм/47 кОм		
	BN1908	TOSH	Dnon x2	$V_{DB0} = 50 \text{ B}; I_D = 100 \text{ mA}; P_D = 200 \text{ mBT}; f_T = 250 \text{ MFu};$	COTTOGS	E1 + D1 + C2 + E2 + D2 + C1





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
XI	RN 1908FE	TOSH	Dnpn x2	$V_{DB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 22 \text{ KOm}/47 \text{ KOM}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
XJ	RN 1609	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 мA; P_D = 300 мВт; f_T = 250 МГц; P_1/P_2 = 47 кОм/22 кОм	000000000000000000000000000000000000000	E1 • B1 • C2 • E2 • B2 • C1
X.J	RN 1909	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 250 \text{ MFL; } R_1/R_2 = 47 \text{ KOm}/22 \text{ KOM}$	SC88	E1 • B1 • C2 • E2 • B2 • C1
XJ	RN 1909FE	TOSH	Dnpn x2	$V_{CB0} = 50 B_1 I_C = 100 \text{mA}; P_0 = 100 \text{mB} \text{T}; f_T = 250 \text{MFu}; P_1/P_2 = 47 \text{KOm}/22 \text{KOM}$		E1 • B1 • C2 • E2 • B2 • C1
XK	RN1610	TOSH	Dnpn x2	$V_{C80} = 50 \text{B;} I_C = 100 \text{mA;} P_D = 300 \text{mBT;} f_T = 250 \text{MFu;} P_1 = 4.7 \text{κOm}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
XK	RN 1910	TOSH	Dnpn x2	$V_{CB0} = 50 B$; $I_C = 100 \text{mA}$; $P_D = 200 \text{mB} \tau$; $f_T = 250 \text{MFu}$; $P_1 = 4.7 \text{kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
XK	RN1910FE	TOSH	Dnpn x2	$V_{C80} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 250 \text{ MFu; } P_T = 4.7 \text{ KOM}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
XM	RN1611	TOSH	Dnpn x2	$V_{CB0} = 50 \text{B;} I_C = 100 \text{mA;} P_D = 300 \text{mBT;} f_T = 250 \text{MFu;} P_T = 10 \text{kOm}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
XM	RN1911	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; f_T = 250 \text{ MFu}; R_1 = 10 \text{ kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
XM	RN1911FE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 250 \text{ MFu; } P_T = 10 \text{ kOm}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
XR	MRF2947RAT1	MOT	npn x2	$V_{CB0} = 20 \text{ B; } I_C = 50 \text{ mA; } P_D = 188 \text{ mBT; } h_{21} = 75150; $ $f_T = 9 \Gamma \Gamma u$	SOT363, SC88	B1 • E1 • C2 • B2 • E2 • C1
XXA	RN1961	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 4.7 \text{ KOM}/4.7 \text{ KOM}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
XXA	RN1961FE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 4.7 \text{ KOm}/4.7 \text{ KOM}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
XXB	RN 1962	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 10 \text{ kOm}/10 \text{ kOm}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
XXB	RN1962FE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 250 \text{ MFL; } R_1/R_2 = 10 \text{ k} 0 \text{ m/} 10 \text{ k} 0 \text{ m}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
XXC	RN 1963	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 22 \text{ KOm}/22 \text{ KOM}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
XXC	RN1963FE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 22 \text{ KOm}/22 \text{ KOM}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
XXD	RN 1964	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 47 \text{ KOm}/47 \text{ KOM}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
XXD	RN1964FE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 47 \text{ k} 0 \text{ m}/47 \text{ k} 0 \text{ m}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
XXE	RN 1965	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 2.2 \text{ kOm/47 kOm}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
XXE	RN 1965FE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 2.2 \text{ kOm/47 kOm}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
XXF	RN 1966	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 4.7 \text{ kOm/47 kOm}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
XXF	RN 1966FE	TOSH	Dnpn x2	$V_{CBB} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 4.7 \text{ KOM/47 KOM}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
XXH	RN 1967	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 250 \text{ MFL; } R_1/R_2 = 10 \text{ kOm}/47 \text{ kOm}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
XXH	RN 1967FE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 250 \text{ MFL; } R_1/R_2 = 10 \text{ kOm}/47 \text{ kOm}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
XXI	RN 1968	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 250 \text{ MFL; } R_1/R_2 = 22 \text{ KOm}/47 \text{ KOM}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
XXI	RN 1968FE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 22 \text{ KOm}/47 \text{ KOM}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
XXJ	RN 1969	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 250 \text{ MFu; } R_1/R_2 = 47 \text{ KOm}/22 \text{ KOM}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
XXJ	RN 1969FE	TOSH	Dnpn x2	V _{CB0} = 50 B; I _C = 100 mA; P _D = 100 mBT; f _T = 250 MFu; R ₁ /R ₂ = 47 κOm/22 κOm		E1 • E2 • B2 • C2 • B1 • C1





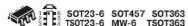
Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
XXK	RN1970	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 250 \text{ MFu; } R_1 = 4.7 \text{ kGm}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
OK	RN1970FE	TOSH	Dnpn x2	V_{CB0} = 50 B; I_C = 100 мA; P_D = 100 мВт; f_T = 250 МГц; R_1 = 4.7 кОм	SOT666	E1 • E2 • B2 • C2 • B1 • C1
COM	RN1971	TOSH	Dnpn x2	$V_{CB0} = 50 B_1 I_C = 100 \text{мA}; P_D = 200 \text{мBT}; f_T = 250 \text{МГц}; R_1 = 10 \text{кОм}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
XXM	RN1971FE	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B}_1 I_C = 100 \text{ mA}; P_D = 100 \text{ mB} \text{ T}_1 f_T = 250 \text{ MFu}_1 R_1 = 10 \text{ kOm}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
ΧP	RN1973	TOSH	Dnpn x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } R_1 = 47 \text{ kOm}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
/0s	CGY121B	SIEM	amp	GaAs; V _{CC} =2.76B; f _{BD} =0.82.5ΓΓц	MW-6	V2/RF-OUT ● RF-GND ● VD1 ● RF- IN ● RF-GND ● VCONTR
Y2	CLY2	SIEM	nFET	GaAs; V _{DS} = 9 B; I _D = 600 mA; P _D = 900 mBt; I _{DSS} = 650 mA	MW-6	G•S•D•D•S•G
Y5s	CGY59	SIEM	amp	GaAs; f ₈₀ = 0.9/1.8 ΓΓ ₄	SOT363, SC88	DC-GND • RF-GND • IN • OUT • RF- GND • VD
Y6s	CGY62	SIEM	amp	GaAs; V _{CC} =2.75 B; f _{BD} =0.22.5ΓΓц	MW-6	OUT • GND • INTERS • IN • GND • GND
Y7	CGY60	SIEM	amp	GaAs; f _{в0} = 1.8 ГГц	MW-6	DC-GND • RF-GND • IN • OUT • RF- GND • VD
Y8	CGY120	SIEM	amp	GaAs; V _{CC} =2.76B; f _{BD} =0.82.5ΓΓц	MW-6	IN • GND • VCONTR • OUT • GND • VD1
Y9s	CGY121A	SIEM	amp	GaAs; V _{CC} =2.76B; f _{BD} =0.82.5ΓΓц	MW-6	V2/RF-OUT ● RF-GND ● VD1 ● RF- IN ● RF-GND ● VCONTR
ſΑ	RN2601	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 4.7 \text{ kOm}/4.7 \text{ kOm}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
YΑ	RN2901	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 4.7 \text{ kOm}/4.7 \text{ kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
YΑ	RN2901FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 4.7 \text{ kOm}/4.7 \text{ kOm}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
ΥB	RN2602	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 10 \text{ kOm}/10 \text{ kOm}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
ΥB	RN2902	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mB} \text{T}; f_T = 200 \text{ MFu}; R_1/R_2 = 10 \text{ kOm}/10 \text{ kOm}$	SC88	
YB	RN2902FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFI; } R_1/R_2 = 10 \text{ KOm}/10 \text{ KOm}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
YC	RN2603	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 22 \text{ kOm}/22 \text{ kOm}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
YC	RN2903	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 22 \text{ kOm}/22 \text{ kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
YC	RN2903FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 100 \text{ mBT}; f_T = 200 \text{ MFL}; R_1/R_2 = 22 \text{ KOm}/22 \text{ KOM}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
YD	RN2604	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 47 \text{ kOm}/47 \text{ kOm}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
ΥD	RN2904	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ мA; } P_D = 200 \text{ мBт; } f_T = 200 \text{ МГц; } R_1/R_2 = 47 \text{ кОм}/47 \text{ кОм}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
ΥD	RN2904FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 47 \text{ kOm}/47 \text{ kOm}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
Æ	RN2605	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBt; } f_T = 200 \text{ MFu; } R_1/R_2 = 2.2 \text{ kOm}/47 \text{ kOm}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
ΥE	RN2905	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; f_T = 200 \text{ MFu}; R_1/R_2 = 2.2 \text{ kOm}/47 \text{ kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
ΥE	RN2905FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBt; } f_T = 200 \text{ MFu; } R_1/R_2 = 2.2 \text{ kOm}/47 \text{ kOm}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
ΥF	RN2606	TOSH	Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 300 mBT; f_T = 200 MFu; R_1/R_2 = 4.7 kOm/47 kOm	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
ΥF	RN2906	TOSH	Dpnp x2	$V_{CBO} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFLI; } R_1/R_2 = 4.7 \text{ kOm}/47 \text{ kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1

fs6 son-6 sot563 1 5 5 Sot363 sot457 sot23-6 1 5 Sot363 sot457 sot57 sot457 sot57 sot457 sot45





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
ΥF	RN2906FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 4.7 \text{ KOm}/47 \text{ KOM}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
ΥH	RN2607	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBT; } f_T = 200 \text{ MFu; } P_1/P_2 = 10 \text{ kOm}/47 \text{ kOm}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
ΥH	RN2907	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 10 \text{ kOm}/47 \text{ kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
/H	RN2907FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBt; } f_T = 200 \text{ MFu; } R_1/R_2 = 10 \text{ kOm}/47 \text{ kOm}$		E1 • B1 • C2 • E2 • B2 • C1
/1	RN2608	TOSH	Dpnp x2	$R_1/R_2 = 22 \text{ KOm}/47 \text{ KOm}$		E1 • B1 • C2 • E2 • B2 • C1
/1	RN2908	TOSH	Dpnp x2	V_{CB0} = 50 B; I_C = 100 мA; P_D = 200 мВт; f_T = 200 МГц; R_1/R_2 = 22 кОм/47 кОм	SC88	E1 • B1 • C2 • E2 • B2 • C1
/I	RN2908FE	TOSH	Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 100 mBT; f_T = 200 MFu; R_1/R_2 = 22 kOm/47 kOm	000000000000000000000000000000000000000	E1 • B1 • C2 • E2 • B2 • C1
IJ	RN2609	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 300 \text{ mBt; } f_T = 200 \text{ MFu; } R_1/R_2 = 47 \text{ kOm}/22 \text{ kOm}$		733 30300 1000 000 000 000
YJ	RN2909	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 47 \text{ kOm/22 kOm}$	SC88	E1 • B1 • C2 • E2 • B2 • C1
Y.J	RN2909FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBt; } f_T = 200 \text{ MFu; } R_1/R_2 = 47 \text{ kOm}/22 \text{ kOm}$		DESCRIPTION NO. NO. OF CORP.
ΥK	RN2610	TOSH	Dpnp x2	$V_{CB0} = 50 B; I_C = 100 \text{мA}; P_D = 300 \text{мBT}; f_T = 200 \text{МГц}; R_T = 4.7 \text{кОм}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
ΥK	RN2910	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBt; } f_T = 200 \text{ MFu; } R_1 = 4.7 \text{ kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
ΥK	RN2910FE	TOSH	Dpnp x2	$V_{CB0} = 50 B; I_C = 100 \text{мA}; P_D = 100 \text{мBT}; f_T = 200 \text{МГц}; R_1 = 4.7 \text{кОм}$		
ΥM	RN2611	TOSH	Dpnp x2	$V_{C80} = 50 B; I_C = 100 \text{mA}; P_D = 300 \text{mBT}; f_T = 200 \text{MFu}; R_1 = 10 \text{kOm}$	SOT23-6	E1 • B1 • C2 • E2 • B2 • C1
ΥM	RN2911	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1 = 10 \text{ kOm}$	SOT363, SC88	E1 • B1 • C2 • E2 • B2 • C1
ΥM	RN2911FE	TOSH	Dpnp x2	$V_{CB0} = 50 B; I_C = 100 \text{mA}; P_D = 100 \text{mBT}; f_T = 200 \text{MFu}; R_1 = 10 \text{kOm}$	SOT666	E1 • B1 • C2 • E2 • B2 • C1
YYA	RN2961	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 4.7 \text{ kOm/}4.7 \text{ kOm}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
YYA	RN2961FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 4.7 \text{ KOm}/4.7 \text{ KOm}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
ΥYΒ	RN2962	TOSH	Dpnp x2	$V_{CB0} = 50 B; I_C = 100 \text{mA}; P_D = 200 \text{mBT}; f_T = 200 \text{MFu}; R_1/R_2 = 10 \text{kOm}/10 \text{kOm}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
YYB	RN2962FE	TOSH	Dpnp x2	$V_{CB0} = 50 B; I_C = 100 \text{mA}; P_D = 100 \text{mBT}; f_T = 200 \text{MFu}; R_1/R_2 = 10 \text{kOm}/10 \text{kOm}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
YYC	RN2963	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 22 \text{ kOm}/22 \text{ kOm}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
YYC	RN2963FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 22 \text{ kOm}/22 \text{ kOm}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
ΛD	RN2964	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 47 \text{ kOm}/47 \text{ kOm}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
ΛD	RN2964FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 47 \text{ KOm}/47 \text{ KOM}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
ΥE	RN2965	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 2.2 \text{ KOm}/47 \text{ KOM}$	SC88	E1 • E2 • B2 • C2 • B1 • C1
YYE	RN2965FE	TOSH	Dpnp x2	$V_{C80} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 2.2 \text{ KOm}/47 \text{ KOM}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
ΥF	RN2966	TOSH	Dpnp x2	$V_{C80} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 4.7 \text{ KOm}/47 \text{ KOm}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
ΥF	RN2966FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 4.7 \text{ KOm}/47 \text{ KOM}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
ΛΉ	RN2967	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 200 \text{ mBT; } f_T = 200 \text{ MFu; } R_1/R_2 = 10 \text{ kOm}/47 \text{ kOm}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1





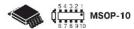
Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6
YYH	RN2967FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 100 \text{ mBT}; f_T = 200 \text{ MFu}; R_1/R_2 = 10 \text{ kOm}/47 \text{ kOm}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
YYI	RN2968	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mB} \text{T}; f_T = 200 \text{ MFu}; R_1/R_2 = 22 \text{ KOm}/47 \text{ KOM}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
YYI	RN2968FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 100 \text{ mBT}; f_T = 200 \text{ MFu}; R_1/R_2 = 22 \text{ KOM}/47 \text{ KOM}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
YYJ	RN2969	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mB} \text{T}; f_T = 200 \text{ MFL}; R_1/R_2 = 47 \text{ kOm}/22 \text{ kOm}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
YYJ	RN2969FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 100 \text{ mB} \text{T}; f_T = 200 \text{ MFu}; R_1/R_2 = 47 \text{ кOm}/22 \text{ кOm}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
YYK	RN2970	TOSH	Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; f_T = 200 MFu; R_1 = 4.7 kOm	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
YYK	RN2970FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 100 \text{ mBT}; f_T = 200 \text{ MFL}; R_1 = 4.7 \text{ KOM}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
YYM	RN2971	TOSH	Dpnp x2	V_{CB0} = 50 B; I_C = 100 mA; P_D = 200 mBT; f_T = 200 MFu; R_1 = 10 kOm	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
YYM	RN2971FE	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D = 100 \text{ mBT; } f_T = 200 \text{ MFu; } R_1 = 10 \text{ kOm}$	SOT666	E1 • E2 • B2 • C2 • B1 • C1
YYS	RN2975	TOSH	Dpnp x2	$V_{CB0} = 50 \text{ B}; I_C = 100 \text{ mA}; P_D = 200 \text{ mBT}; f_T = 200 \text{ MFu}; R_1/R_2 = 2.2 \text{ KOM}/10 \text{ KOM}$	SOT363, SC88	E1 • E2 • B2 • C2 • B1 • C1
Z1	EMZ1	ROHM	npn/pnp	$V_{CB0} = 60 \text{ B}; I_C = 150 \text{ mA}; P_0 = 150 \text{ mBT}; h_{21} > 120$	SOT563, EMT6	E1 • B1 • C2 • E2 • B2 • C1
Z1	IMZ1A	ROHM	npn/pnp	V _{CB0} =60 B; I _C =150 mA; P _D =300 mBt; h ₂₁ >120	SOT23-6	C1•B2•E2•C2 •B1•E1
Z1	UMZ1N	ROHM	pnp(2)+npn (1)	$V_{CB0} = 50 \text{ B; } I_C = 100 \text{ mA; } P_D \text{ (com.)} = 300 \text{ mBT; } h_{21} = 120560; f_T > 400 \text{ MFц}$	SOT363, SC88	E1 •B1•C2•E2•B2•C1
Z2	EMZ2	ROHM	npn/pnp	$V_{CB0} = 60 \text{ B}; I_C = 150 \text{ mA}; P_D = 150 \text{ mBT}; h_{21} > 120$	SOT563, EMT6	E1 • B1 • B2 • C2 • E2 • C1
Z2	IMZ2A	ROHM	npn/pnp	$V_{CB0} = 60 \text{ B}, I_C = 150 \text{ mA}, P_D = 300 \text{ mBT}, h_{21} > 120$	SOT23-6	C1 • E2 • C2 • B2 • B1 • E1
Z2	UMZ2N	ROHM	pnp(1)+npn (2)	V_{CB0} =50 B; I_C =100 mA; P_D (com.) =300 mBT; h_{21} =120560; f_T >180 MF $_U$	SOT363, SC88	E1 •B1 •B2 • C2 • E2 • C1
Z4	IMZ4	ROHM	npn/pnp	$V_{CB0} = 40 \text{ B}; I_C = 500 \text{ mA}; P_D = 300 \text{ mBT}; h_{21} > 120$	SOT23-6	C1•B2•E2•C2 •B1•E1
ZS20	ZHCS2000	ZETEX	shd	V_R <40B; I_F <2A; V_F (I_F =3A)<0.615B; I_B <300 mKA; C_D =50 n Φ	SOT23-6	K•K•A•A•K•K



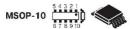
MSOP/SOP-8/10

Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
#DBB	AD5304BRMZ	AD	DAC	4x8-pasp.; SPI/Microwire; V ₀₀ = 2.55.5 B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
#DCA	AD5314ARMZ	AD	DAC	4x10-pasp.; SPI/Microwire; V _{DD} = 2.55.5B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
#DCB	AD5314BRMZ	AD	DAC	4x10-pasp.; SPI/Microwire; V _{DD} = 2.55.5B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
#DDB	AD5324BRMZ	AD	DAC	4x12-pasp.; SPI/Microwire; V _{DO} = 2.55.5B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
#HCA	AD8062ARMZ	AD	dOA	$f_{BD} = 320 \text{ MFu}; P_D = 75 \text{ mBT}; V_{DO} = 2.78 \text{ B}$	MSOP-8	VOUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • VOUT2 • +VS
0412	LT1004CS8-1.2	LT	vref	V _{DUT} = 1.2 B; ACC = ±4 mB	SOP-8	n.c. • n.c. • n.c. • GND • n.c. • VOUT • n.c. • VOUT
0412I	LT1004IS8-1.2	LT	vref	V _{DUT} = 1.2 B; ACC = ±4 mB	SOP-8	n.c. • n.c. • n.c. • GND • n.c. • VOUT • n.c. • VOUT
0425	LT1004CS8-2.5	LT	vref	V _{DUT} = 2.5 B; ACC = ±20 MB	SOP-8	n.c. • n.c. • n.c. • GND • n.c. • VOUT • n.c. • VOUT
04251	LT1004IS8-2.5	LT	vref	V _{DUT} = 2.5 B; ACC = ±20 MB	SOP-8	n.c. • n.c. • n.c. • GND • n.c. • VOUT • n.c. • VOUT
1001	LT1001CS8	LT	OA	V _{DSI} < 60 MKB; V _{DD} = ± 15 B; P _D < 80 MBT	SOP-8	VOSTRIM • -IN • +IN • V- • n.c. • OUT • V+ • VOSTRIM
1006	LT1006S8	LT	OA	V _{DSI} < 50 MKB; V _{DD} > 2.7 B; P _D < 80 MBT	SOP-8	VOSTRIM • -IN • +IN • V- • VOSTRIM • OUT • V+ • ISY SET
1007	LT1007CS8	LT	OA	V _{DSI} < 60 MKB; V _{DD} > 2.7 B; P _D < 160 MBT	SOP-8	VOSTRIM • -IN • +IN • V- • n.c. • OUT • V+ • VOSTRIM
1007I	LT1007IS8	LT	OA	V _{DSI} < 60 MKB; V _{DD} > 2.7 B; P _D < 160 MBT	SOP-8	VOSTRIM • -IN • +IN • V- • n.c. • OUT • V+ • VOSTRIM
1008	LT1008S8	LT	OA	V _{DSI} < 180 mkB; V _{DD} > 2.7B	SOP-8	COMP1 • -IN • +IN • V- • n.c. • OUT • V+ • COMP2
1009	LT1009S8	LT	vref	V _{DUT} = 2.5 B; ACC < 0.2 %; T _{AMB} = 070 °C	SOP-8	n.c. • n.c. • n.c. • (-) • ADJ • (+) • n.c. • (+)
1009l	LT1009IS8	LT	vref	V _{DUT} = 2.5 B; ACC < 0.2 %; T _{AMB} = -4085 °C	SOP-8	n.c. • n.c. • n.c. • (-) • ADJ • (+) • n.c. • (+)
1011	LT1011CS8	LT	cmp	V _{DSI} < 0.5 MB; V _{DD} = ± 15B; T _{AMB} = 070 °C	SOP-8	GND • INPUT • INPUT • V- • BAL • BAL/STR • OUTPUT • V+
101 1AJ	LT1011AIS8	LT	cmp	V _{OSI} < 0.5 MB; V ₀₀ = ± 15B; T _{AMB} = -55125 °C	SOP-8	GND • INPUT • INPUT • V- • BAL • BAL/STR • OUTPUT • V+
101 1I	LT1011IS8	LT	стр	V _{DSI} < 0.5 MB; V _{DD} = ± 15B; T _{AMB} = -4085°C	SOP-8	GND • INPUT • INPUT • V- • BAL • BAL/STR • OUTPUT • V+
1012	LT1012S8	LT	OA	V _{DSI} < 25 мкВ; V _{DD} = ± 15 В; I _D < 600 мкА; T _{AMB} = 070 °C	SOP-8	VOSTRIM • -IN • +IN • V- • OVER COMP • OUT • V+ • VOSTRIM
1012A	LT1012ACS8	LT	OA	V_{DSI} < 25 mKB; V_{DD} = ± 15 B; I_D < 600 mKA; T_{AMB} = 070 °C	SOP-8	VOSTRIM • -IN • +IN • V- • OVER COMP • OUT • V+ • VOSTRIM
1012AJ	LT1012AIS8	LT	OA	V _{DSI} < 25 мкВ; V _{DD} = ± 15 В; I _D < 600 мкА; T _{AMB} = -4085 °C	SOP-8	VOSTRIM • -IN • +IN • V- • OVER COMP • OUT • V+ • VOSTRIM
1012I	LT1012IS8	LT	OA	V _{DSI} < 25 mkB; V _{DD} = ± 15 B; I _D < 600 mkA; T _{AMB} = -4085 °C	SOP-8	VOSTRIM • -IN • +IN • V- • OVER COMP • OUT • V+ • VOSTRIM
1013	LT1013DS8	LT	dOA	V _{DSI} < 150 mKB; V _{DD} = ± 15B; I _D < 550 mKA; T _{AMB} = 070 °C	SOP-8	+INA • V- • +INB • -INB • OUTB • V+ • OUTA • -INA
1013I	LT1013IS8	LT	dOA	V _{DSI} < 150 mkB; V _{DD} = ± 15B; I _D < 550 mkA; T _{AMB} = -4085°C	SOP-8	+INA • V - • +INB • -INB • OUTB • V+ • OUTA • -INA
1016	LT1016CS8	LT	стр	V _{DSI} < 0.5 MB; V _{DD} = 5/±5 B; t _{PD} = 10 HC; T _{AMB} = 070 °C	SOP-8	V+ • +IN • -IN • V- • LAT ENBL • GND • Q OUT • Q OUT
1016	LT1016IS8	LT	стр	V _{DSI} < 0.5 MB; V _{DD} = 5/± 5 B; t _{PD} = 10 HC; T _{AMB} = -4085 °C	SOP-8	V+ • +IN • -IN • V- • LAT ENBL • GND • Q OUT • Q OUT
1017	LT1017CS8	LT	cmp x2	V _{DSI} < 1 MB; V _{DO} = 1.140 B; T _{AMB} = 070 °C	SOP-8	HN A • V - • HN B • -IN B • OUT B • V+ • OUT A • -IN A





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
10171	LT1017IS8	LT	cmp x2	V _{OSI} <1 mB; V _{DD} = 1.140B; T _{AMB} = -4085°C	SOP-8	+IN A • V - • +IN B • -IN B • CUT B • V + • OUT A • -IN A
1018	LT1018CS8	LT	cmp x2	V _{DSI} <1 mB; V _{DD} = 1.140B; T _{AMB} = 070 °C	SOP-8	+IN A • V− • +IN B • −IN B • CUT B • V+ • CUT A • −IN A
1026	LT1026CS8	LT	vcon	V _{OUT} = ± 18 B; I _{OUT} > 10 mA; T _{AMB} = 070 °C	SOP-8	C1- • C2+ • C2- • - VOUT • GND • VIN • C1+ • + VOUT
10261	LT1026IS8	LT	vcon	$V_{OUT} = \pm 18 \text{ B; } I_{OUT} > 10 \text{ mA; } T_{AMB} = -4085^{\circ}\text{C}$	SOP-8	C1- • C2+ • C2- • - VOUT • GND • VIN • C1+ • + VOUT
1027C5	LT1027CCS8-5	LT	vref	V _{OUT} = 5 B; T _{AMB} = 070 °C; T _{CVOUT} < 3 ppm/°C	SOP-8	NR • GND • VTRIM • VOUT • n.c. • n.c. • n.c. • VIN
1027D5	LT1027DCS8-5	LT	vref	V _{OUT} = 5 B; T _{AMB} = 070 °C; T _{CVOUT} < 5 ppm/°C	SOP-8	NR • GND • VTRIM • VOUT • n.c. • n.c. • n.c. • VIN
1027E5	LT1027ECS8-5	LT	vref	T _{CVOUT} < 7.5ppm/°C	SOP-8	NR • GND • VTRIM • VOUT • n.c. • n.c. • n.c. •
METER .	LT1028CS8	LT	OA	V_{OSI} <40 mKB; V_{DO} = ± 15 B; I_{D} <10.5 mA; T_{AMB} = -4085 °C	SOP-8	VOSTRIM • -IN • +IN • V- • OVER COMP • OUT • V+ • VOSTRIM
1034112	LT1034IS8-1.2	LT	vref x2	V _{OUT1} = 1.2B; V _{OUT2} = 7B; T _{AMB} = -4085 °C	SOP-8	n.c. • n.c. • n.c. • GND • 7V • 2.5V • n.c. • 2.5V
1037	LT1037CS8	LT	CA	V _{OSI} <60 мкВ; V _{DO} >2.7В; P _D <160 мВт	SOP-8	VOSTRIM • -IN • +IN • V- • n.c. • OUT • V+ • VOS TRIM
1054	LT1054CS8	LT	vcon + reg	V _{CC} = 3.515 B; I _{OUT} = 100 mA; T _{AMB} = 0100 °C	SOP-8	FB/SHDN • CAP+ • GND • CAP- • VOUT • VREF • OSC • V+
1054A	LT1054ACS8	LT	vcon + reg	V _{CC} = 3.515 B; I _{OUT} = 100 mA; T _{AMB} = 0100 °C	SOP-8	FB/SHDN • CAP+ • GND • CAP- • VOUT • VREF • OSC • V+
10541	LT1054IS8	LT	vcon + reg	V _{CC} =3.515B; I _{OUT} =100mA; T _{AMB} =-40100°C	SOP-8	FB/SHDN • CAP+ • GND • CAP- • VOUT • VREF • OSC • V+
1054L	LT1054LCS8	LT	vcon + reg	V _{CC} = 3.57 B; I _{DUT} = 100 mA; T _{AMB} = 0100 °C	SOP-8	FB/SHDN • CAP+ • GND • CAP- • VOUT • VREF • OSC • V+
1055	LT1055S8	LT	OA	V _{OSI} < 150 мкВ; V _{DO} = ± 15 В; I _D < 7 мА; Т _{АМВ} = 070 °C	SOP-8	BAL • -IN • +IN • V - • BAL • OUT • V + • n.c.
1056	LT1056S8	LT	OA	V _{OSI} <150 мкВ; V _{OO} = ± 15 В; I _D < 7 мА; Т _{АМВ} = 070 °C	SOP-8	BAL • -IN • +IN • V - • BAL • OUT • V+ • n.c.
1057	LT1057S8	LT	dOA	V _{OSI} <450 mkB; V _{DO} = ± 15 B; I _D < 2.8 mA; T _{AMB} = 070 °C	SOP-8	+IN A • V - • +IN B • -IN B • OUT B • V+ • OUT A • -IN A
1057I	LT1057IS8	LT	dOA	V _{OSI} <450 mkB; V _{DO} = ± 15 B; I _D <2.8 mA; T _{AMB} = -4085 °C	SOP-8	+IN A • V - • +IN B • -IN B • OUT B • V+ • OUT A • -IN A
1072	LT1072CS8	LT	reg	V _{IN} = 360B; f _{SW} = 40 κΓц	SOP-8	GND • VC • FB • n.c. • VIN • E1 • VSW • E2
1073	LT1073CS8	LT	dodo	V _{IN} = 130 В; I _S < 130 мкА	SOP-8	ILIM • VIN • SW1 • SW2 • GND • A0 • SET • FB/SENSE
	LT1073CS8-12	LT	dede	V _{IN} = 130B; V _{DUT} = 12B; I _S < 130 мкА	SOP-8	ILIM • VIN • SW1 • SW2 • GND • A0 • SET • FB/SENSE
	LT1073CS8-5	LT	dcdc	V _{IN} = 130B; V _{DUT} = 5B; I _S < 130 мкА	SOP-8	IUM • VIN • SW1 • SW2 • GND • A0 • SET • FB/SENSE
1077	LT1077S8	LT	OA	V_{OSI} < 40 mKB; V_{DO} = 5B; I_D < 68 mKA; T_{AMB} = 070 °C	SOP-8	VOS TRIM • -IN • +IN • V- • n.c. • OUT • V+ • VOS TRIM
	LT1077IS8	LT	CA	4085°C	SOP-8	VOS TRIM • -IN • +IN • V- • n.c. • OUT • V+ • VOS TRIM
1078	LT1078S8	LT	dOA	V _{OSI} <70 mkB; V _{DO} = 5B; I _D <68 mkA; T _{AMB} = 070 °C	SOP-8	+IN A • V - • +IN B • -IN B • CUT B • V + • CUT A • -IN A
10781	LT1078IS8	LT	dOA	4085°C	SOP-8	+IN A • V - • +IN B • -IN B • OUT B • V+ • OUT A • -IN A
100001	LT1109CS8-5	LT	dodo	V _{IN} = 320B; V _{DUT} = 5B; I _S < 320 мкА; Т _{АМВ} = 070 °C °C	SOP-8	VIN • n.c. • SW • GND • n.c. • n.c. • SHUTDOWN • SENSE
10912	LT1109CS8-12	LT	dede	V _{IN} = 320B; V _{DUT} = 12B; I _S < 320 мкА; Т _{АМВ} = 070 °C°C	SOP-8	VIN • n.c. • SW • GND • n.c. • n.c. • SHUTDOWN • SENSE
1097	LT1097S8	LT	OA	V _{OSI} <50 мкВ; V _{DO} = ± 15 В; I _D < 0.7 мА; Т _{АМВ} =-4085 °C	SOP-8	VOS TRIM • -IN • +IN • V- • OVER COMP • OUT • V+ • VOS TRIM
11012	LT1110CS8-12	LT	dodo	V _{IN} = 130B; V _{DUT} = 12B; T _{AMB} = 070°C °C	SOP-8	ILIM • VIN • SW1 • SW2 • GND • AD • SET • FB/SENSE



Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
1107	LT1107CS8	LT	dcdc	V _{IN} = 230 B; I _S < 450 mKA; T _{AMB} = 070 °C	SOP-8	ILIM • VIN • SW1 • SW2 • GND • AO • SET • FB/SENSE
110712	LT1107CS8-12	LT	dcdc	V _{IN} =230 B; V _{CUT} = 12 B; I _S < 450 mkA; T _{AMR} = 070 °C °C	SOP-8	ILIM • VIN • SW1 • SW2 • GND • AO • SET • FB/SENSE
11075	LT1107CS8-5	LT	dcdc	V _{IN} =230 B; V _{OUT} =5 B; I _S <450 mkA; T _{AMB} =070 °C °C	SOP-8	ILIM • VIN • SW1 • SW2 • GND • AO • SET • FB/SENSE
11071	LT1107IS8	LT	dcdc	V _{IN} = 230 B; I _S < 450 mmA; T _{AMB} = -4085 °C	SOP-8	ILIM • VIN • SW1 • SW2 • GND • AO • SET • FB/SENSE
108	LT1108CS8	LT	dcdc	V _{IN} = 230 B; I _S < 110 mmA; T _{AMB} = 070 °C	SOP-8	ILIM • VIN • SW1 • SW2 • GND • A0 • SET • FB/SENSE
1081	LT1108CS8-12	LT	dcdc	V _{IN} =230 B; V _{OUT} =12 B; I _S < 110 mrA; T _{AMB} =070 °C °C	SOP-8	ILIM • VIN • SW1 • SW2 • GND • A0 • SET • FB/SENSE
1085	LT1108CS8-5	LT	dcdc	V _{IN} = 230 B; V _{OUT} = 5 B; I _S < 110 mkA; T _{AMB} = 070 °C °C	SOP-8	ILIM • VIN • SW1 • SW2 • GND • A0 • SET • FB/SENSE
1109	LT1109CS8	LT	dcdc	V _{IN} = 320 B; I _S < 320 mkA; T _{AMB} = 070 °C	SOP-8	VIN • n.c. • SW • GND • n.c. • n.c. • SHUTDOWN • SENSE
1109A	LT1109ACS8	LT	dede	V_{IN} = 320 B; I_S < 320 MKA; T_{AMB} = 070 °C	SOP-8	VIN • n.c. • SW • GND • n.c. • n.c. • SHUTDOWN • SENSE
1109A1	LT1109ACS8-12	LT	dede	V _{IN} = 320 B; V _{OUT} = 12 B; I _S < 320 mkA; T _{AMB} = 070 °C °C	SOP-8	VIN • n.c. • SW • GND • n.c. • n.c. • SHUTDOWN • SENSE
1109A5	LT1109ACS8-5	LT	dcdc	V _{IN} =320 B; V _{OUT} =5 B; I _S < 320 мкА; Т _{АМВ} = 070 °C °C	SOP-8	VIN • n.c. • SW • GND • n.c. • n.c. • SHUTDOWN • SENSE
1110	LT1110CS8	LT	dcdc	V _{IN} = 130 B; T _{AMB} = 070 °C	SOP-8	ILIM • VIN • SW1 • SW2 • GND • A0 • SET • FB/SENSE
11105	LT1110CS8-5	LT	dede	V _{IN} = 130 B; V _{OUT} = 5 B; T _{AMB} = 070 °C °C	SOP-8	ILIM • VIN • SW1 • SW2 • GND • A0 • SET • FB/SENSE
1111	LT1111CS8	LT	dcdc	V _{IN} = 230 B; T _{AMB} = 070 °C	SOP-8	ILIM • VIN • SW1 • SW2 • GND • A0 • SET • FB/SENSE
11111	LT1111CS8-12	LT	dcdc	V _{IN} = 230 B; V _{OUT} = 12 B; T _{AMB} = 070 °C °C	SOP-8	ILIM • VIN • SW1 • SW2 • GND • A0 • SET • FB/SENSE
11115	LT1111CS8-5	LT	dcdc	V _{IN} = 230 B; V _{OUT} = 5 B; T _{AMB} = 070 °C °C	SOP-8	ILIM • VIN • SW1 • SW2 • GND • A0 • SET • FB/SENSE
1111L	LT1111IS8	LT	dede	V _{IN} =230 B; T _{AMB} = -4085 °C	SOP-8	ILIM • VIN • SW1 • SW2 • GND • A0 • SET • FB/SENSE
1112	LT1112S8	LT	dOA	V_{DS} < 60 mkB; V_{DD} = ± 15 B; I_D < 400 mkA; T_{AMB} = 070 °C	SOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
11121	LT1112IS8	LT	dOA	V _{DSI} < 60 mKB; V _{DD} = ± 15 B; I _D < 400 mKA; T _{AMB} = -4085 °C	SOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
1113	LT1113CS8	LT	dOA	JFET; $V_{OSI} < 1.5 \text{ mB}$; $V_{DO} = \pm 15 \text{ B}$; $I_O < 6.5 \text{ mA}$; $T_{AMB} = 070 ^{\circ}\text{C}$	SOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
1116	LT1116CS8	LT	стр	$V_{OSI} < 3.5 \text{ MB}; V_{DO} = 5/\pm 5 \text{ B}; t_{PO} = 12 \text{ HC}; T_{AMB} = 070 ^{\circ}\text{C}$	SOP-8	V+ •+IN • -IN • V- • LAT ENBL • GND • Q OUT • Q OUT
1118	LT1118CS8	LT	reg	LDO; V _{IN} < 15 B; I _{OUT} = 800 mA	SOP-8	GND • n.c. • EN • FB • IN • OUT • IN • GND
111825	LT1118CS8-2.5	LT	reg	LDO; V _{IN} < 15 B; V _{DUT} = 2.5 B; I _{DUT} = 800 mA	SOP-8	IN • CUT • GND • IN • n.c. • GND • GND • EN
111828	LT1118CS8-2.85	LT	reg	LDO; V _{IN} < 15 B; V _{DUT} = 2.85 B; I _{DUT} = 800 mA	SOP-8	IN • OUT • GND • IN • n.c. • GND • GND • EN
11185	LT1118CS8-5	LT	reg	LDO; V _{IN} < 15 B; V _{DUT} = 5 B; I _{DUT} = 800 mA	SOP-8	IN • CUT • GND • IN • n.c. • GND • GND • EN
1128	LT1128CS8	LT	OA	V_{OSI} < 40 m/kB; V_{DD} = ± 15 B; I_D < 10.5 mA; T_{AMB} = -4085°C	SOP-8	VOSTRIM • -IN • +IN • V- • OVER COMP • OUT • V+ • VOSTRIM
1905	LT1019CS8-5	LT	vref	V _{DUT} = 5 B; ACC < 0.2%; T _{AMB} = 070 °C	SOP-8	i.c. • INPUT • TEMP • GND • TRIM • OUTPUT • i.c. • i.c.
1910	LT1019CS8-10	LT	vref	V _{DUT} = 10 B; ACC < 0.2%; T _{AMB} = 070 °C	SOP-8	i.c. • INPUT • TEMP • GND • TRIM • OUTPUT • i.c. • i.c.
1925	LT1019CS8-2.5	LT	vref	V _{OUT} = 2.5 B; ACC < 0.2 %; T _{AMB} = 070 °C	SOP-8	i.c. • INPUT • TEMP • GND • TRIM • OUTPUT • i.c. • i.c.
1945	LT1019CS8-4.5	LT	vref	V _{DUT} = 4.5 B; ACC < 0.2 %; T _{AMB} = 070 °C	SOP-8	i.c. • INPUT • TEMP • GND • TRIM • OUTPUT • i.c. • i.c.
19A05	LT1019ACS8-5	LT	vref	V _{DUT} = 5 B; ACC < 0.05 %; T _{AMB} = 070 °C	SOP-8	i.c. • INPUT • TEMP • GND • TRIM • OUTPUT • i.c. • i.c.





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
19A25	LT1019ACS8-2.5	LT	vref	V _{OUT} = 2.5 B; ACC < 0.05 %; T _{AMB} = 070 °C	SOP-8	i.c. • INPUT • TEMP • GND • TRIM • CUTPUT • i.c. • i.c.
19AI05	LT1019AIS8-5	LT	wref	V _{OUT} = 5 B; ACC < 0.05%; T _{AMB} = -4085°C	SOP-8	i.c. • INPUT • TEMP • GND • TRIM • CUTPUT • i.c. • i.c.
19AI25	LT1019AIS8-2.5	LT	vref	V _{OUT} = 2.5 B; ACC < 0.05 %; T _{AMB} = -4085 °C	SOP-8	i.c. • INPUT • TEMP • GND • TRIM • CUTPUT • i.c. • i.c.
19105	LT1019IS8-5	LT	vref	V _{OUT} = 5 B; ACC < 0.2%; T _{AMB} = -4085 °C	SOP-8	i.c. • INPUT • TEMP • GND • TRIM • OUTPUT • i.c. • i.c.
19125	LT1019IS8-2.5	LT	vref	V _{OUT} = 2.5 B; ACC < 0.2 %; T _{AMB} = -4085 °C	SOP-8	i.c. • INPUT • TEMP • GND • TRIM • OUTPUT • i.c. • i.c.
2105	LT1021DCS8-5	LT	vref	V _{OUT} = 5 B; T _{AMB} = 070 °C	SOP-8	i.c. • VIN • i.c. • GND • TRIM • VOUT • i.c. • i.c.
2107	LT1021DCS8-7	LT	vref	V _{OUT} = 7 B; T _{AMB} = 070 °C	SOP-8	i.c. • VIN • i.c. • GND • TRIM • VOUT • i.c. • i.c.
2110	LT1021DCS8-10	LT	vref	V _{OUT} = 10 B; T _{AMB} = 070 °C	SOP-8	i.c. • VIN • i.c. • GND • TRIM • VOUT • i.c. • i.c.
3401	LT1034CS8-1.2	LT	vref x2	V _{OUT1} = 1.2B; V _{OUT2} = 7B; T _{AMB} = 070 °C	SOP-8	n.c. • n.c. • n.c. • GND • 7V • 2.5V • n.c. • 2.5V
3402	LT1034CS8-2.5	LT	vref x2	V _{OUT1} = 2.5B; V _{OUT2} = 7B; T _{AMB} = 070 °C	SOP-8	n.c. • n.c. • n.c. • GND • 7V • 2.5V • n.c. • 2.5V
34102	LT1034IS8-2.5	LT	vref x2	V _{OUT1} = 2.5B; V _{OUT2} = 7B; T _{AMB} = -4085 °C	SOP-8	n.c. • n.c. • n.c. • GND • 7V • 2.5V • n.c. • 2.5V
37518	MC33375D-1.8	ON	reg	LDO; V _{IN} = 2.513 B; V _{OUT} = 1.8 B; I _{OUT} = 300 mA	SOP-8	IN • GND • GND • ON/OFF • n.c. • GND • GND • OUT
37525	MC33375D-2.5	ON	reg	LDO; V _{IN} = 2.5 13 B; V _{OUT} = 2.5 B; I _{OUT} = 300 MA	SOP-8	IN • GND • GND • ON/OFF • n.c. • GND • GND • OUT
37530	MC33375D-3.0	ON	reg	LDO; V _{IN} = 2.513 B; V _{OUT} = 3.0 B; I _{OUT} = 300 MA	SOP-8	IN ◆GND ◆GND ◆ ON/OFF ◆ n.c. ◆GND ◆ GND ◆ OUT
37533	MC33375D-3.3	ON	reg	LDO; V _{IN} = 2.5 13 B; V _{OUT} = 3.3 B; I _{OUT} = 300 MA	SOP-8	IN ◆GND ◆GND ◆ ON/OFF ◆ n.c. ◆GND ◆ GND ◆ OUT
37550	MC33375D-5.0	ON	reg	LDO; V _{IN} = 2.513 B; V _{OUT} = 5.0 B; I _{OUT} = 300 mA	SOP-8	IN • GND • GND • ON/OFF • n.c. • GND • GND • OUT
5812	MRF5812	MOT	npn	V _{CBD} =30B; I _C =200mA; P _D =1670mBr; h ₂₁ =30200; f _T =5.5 ITu	SOP-8	E•C•C•E•E•B•B•E
5943	MRF5943	MOT	npn	$V_{CB0} = 40B$; $I_C = 400 \text{ mA}$; $P_D = 1B\tau$; $I_{D1} = 25200$; $I_T = 1.3 \Gamma\Gamma\text{U}$	SOP-8	E•C•C•E•E•B•B•E
A0R	AD8532ARMZ	AD	dOA	f _{BD} =3 MFu; P _D =12 MBT; V _{DD} =2.76B	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
A1A	OP777ARM	AD	OA	V _{DD} =2.730/±1.35±15 В; I _S =320 мкА; V _{DSI} <200 мкВ	MSOP-8	n.c. • -IN • +IN • V- • n.c. • OUT • V+ • n.c.
A34	OPA234EA	П	OA	V_{DD} = 2.736/±1.35±18 B; I _S = 300 mKA; V_{DSI} < ±350 mKB	MSOP-8	OFF TRIM • -IN • +IN • V- • OFF TRIM • OUT • V+ • n.c.
A4	NLAS323US	ON	asw	2x SPST; R _{ON} < 55 Om; V _{DO} = 2.76.0 B	US-8	NO1 • COM1 • IN2 • GND • NO2 • COM2 • IN1 • VCC
A40A	OPA2340EA	TI	dOA	R-R; V_{DD} = 2.75.5 B; f_{BD} = 5.5 MFu; I_S = 1.1 MA; V_{CS} < ±0.5 MB	MSOP-8	OUT A • -IN A • +IN A • V- • +IN B • -IN B • OUT B • V+
A44	OPA2244EA	TI	dOA	V _{DD} = 2.236/±1.1±18 B; I _S = 70 мкA; V _{DSI} < ±2 мВ	MSOP-8	OUT A • -IN A • +IN A • V- • +IN B • -IN B • OUT B • V+
A5A	AD8529ARU	AD	dOA	f _{BD} =8 MFu; P _D =24 MBT; V _{DO} =2.712B	MSOP-8	OUT A • -IN A • +IN A • V- • +IN B • -IN B • OUT B • V+
Α7	OPA2337EA	TI	dOA	R-R; V _{DD} =2.55.5B; f _{BD} =3MFu; I _S =2mA; V _{DS} (±3.5mB	SOT23-8	OUT A • -IN A • +IN A • V- • +IN B • -IN B • OUT B • V+
A8	OPA2338EA	TI	dOA	R-R; V _{DD} =2.55.5B; f _{BD} =12.5МГц; I _S =2мA; V _{DS} <±3.5мВ	SOT23-8	OUT A • -IN A • +IN A • V • +IN B • -IN B • OUT B • V+
AAAA	MAX1792EUA18	MAX	reg	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 1.8/1.255 B; I _{OUT} = 500 MA	MSOP-8	IN • IN • RST • SHDN • GND • SET • OUT • OUT
AAAA	MAX4451EKA	MAX	dOA	R-R; V _{DD} =4.511/±2.25±5.5B; f _{BD} =210 MFu; V _{DS} <26 мB	SOT23-8	CUTA • INA- • INA+ • VEE • INB+ • INB- • CUTB • VCC

MSOP-10 (5 4 3 2 1) (6 7 8 9 10)



Код	Типономинал	5	ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
AAAB	MAX1792EUA25	MAX	reg	LDO; V _{IN} = 2.55.5 B; V _{OUT} = 2.5/1.255B; I _{OUT} = 500 MA	MSOP-8	IN • IN • RST • SHDN • GND • SET • OUT • OUT
AAAB	MAX4453EZA	MAX	dOA	R-R; V _{DD} = 2.75.25 B; f _{BD} = 200 MFu; V _{DSI} < 12 MB	TSOT23- 8	OUTA • INA- • INA+ • VEE • INB+ • INB- • OUTB • VCC
AAAC	MAX1792EUA33	MAX	reg	LDO; V _{IN} = 2.55.5 B; V _{DUT} = 3.3/1.255 B; I _{DUT} = 500 MA	MSOP-8	IN • IN • RST • SHDN • GND • SET • OUT • OUT
AAAC	MAX5222EKA	MAX	DAC	2x8-pasp.; SPI/QSPI/Microwire; V _{DD} =2.75.5B	SOT23-8	CS • GND • VDD • SCLK • CUTA • CUTB • REF • DIN
AAAD	MAX1792EUA50	MAX	reg	LDO; V _{IN} = 2.55.5 B; V _{DUT} = 5.0/1.255B; I _{DUT} = 500 MA	MSOP-8	IN • IN • RST • SHDN • GND • SET • OUT • OUT
AAAD	MAX9077EKA	MAX	cmp x2	R-R; V _{DSI} < ±8 mB; V _{DC} = 2.15.5 B; I _{DC} < 13 mkA	SOT23-8	OUTA • GND • INA- • INA+ • INB+ • INB- • OUTB • VCC
AAAE	MAX1792EUA15	MAX	reg	LDO; V _{IN} =2.55.5B; V _{DUT} =1.5/1.255B; I _{DUT} =500 mA	MSOP-8	IN • IN • RST • SHDN • GND • SET • OUT • OUT
AAAE	MAX4541EKA	MAX	asw	2xSPST; R _{ON} < 75 Ом; V _{OO} = 2.712 В	SOT23-8	NO1 • V+ • IN2 • COM2 • NO2 • GND • IN1 • COM1
AAAF	MAX1792EUA20	MAX	reg	LDO; V _{IN} =2.55.5B; V _{DUT} =2.0/1.255B; I _{DUT} =500 MA	MSOP-8	IN • IN • RST • SHDN • GND • SET • OUT • OUT
AAAF	MAX4542EKA	MAX	asw	2xSPST; R _{DN} < 75 Ом; V _{DO} = 2.712 В	SOT23-8	NC1 • V+ • IN2 • COM2 • NC2 • GND • IN1 • COM1
AAAG	MAX4543EKA	MAX	asw	2xSPST; R _{DN} < 75 Ом; V _{DO} = 2.712 В	SOT23-8	NO1 • V+ • IN2 • COM2 • NC2 • GND • IN1 • COM1
AAAH	MAX6365LKA46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAI	MAX6365LKA44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25.5 B; I _{CC} < 50 mKA	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAJ	MAX6365LKA31	MAX	mrc	V _{TR} =3.08 B; V _{DD} =1.25.5 B; I _{CC} < 50 мкА	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
aaak	MAX6365LKA29	MAX	mrc	V _{TR} =2.93 B; V _{DD} =1.25.5 B; I _{CC} < 50 мкА	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAL	MAX6365LKA26	MAX	mrc	V _{TR} = 2.63 B; V _{DD} = 1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAM	MAX6365LKA23	MAX	mrc	V _{TR} = 2.32 B; V _{DD} = 1.25.5 B; I _{CC} < 50 мкА	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
aaan	MAX6365PKA46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} <50 MKA	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAO	MAX6365PKA44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAP	MAX6365PKA31	MAX	mrc	V _{TR} =3.08 B; V _{DD} =1.25.5 B; I _{CC} < 50 mKA	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAQ	MAX6365PKA29	MAX	mrc	V _{TR} =2.93 B; V _{DD} =1.25.5 B; I _{CC} ≤50 MKA	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAR	MAX6365PKA26	MAX	mrc	V _{TR} = 2.63 B; V _{DD} = 1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAS	MAX6365PKA23	MAX	mrc	V _{TR} =2.32 B; V _{DD} =1.25.5 B; I _{CC} < 50 mKA	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAT	MAX6365HKA46	MAX	mrc	V _{TR} = 4.63 B; V _{DD} = 1.25.5 B; I _{CC} < 50 mkA	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAU	MAX6365HKA44	MAX	mrc	V _{TR} = 4.38 B; V _{DD} = 1.25.5 B; I _{CC} < 50 mkA	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAV	MAX6365HKA31	MAX	mrc	V _{TR} = 3.08 B; V _{DD} = 1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAW	MAX6365HKA29	MAX	mrc	V _{TR} = 2.93 B; V _{DD} = 1.25.5 B; I _{CC} < 50 MKA	S0T23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAX	MAX6365HKA26	MAX	mrc	V _{TR} = 2.63 B; V _{DD} = 1.25.5 B; I _{CC} < 50 mkA	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT
AAAY	MAX6365HKA23	MAX	mrc	V _{TR} = 2.32 B; V _{DD} = 1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • MR • VCC • OUT • BATT • CE OUT





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
AAAZ	MAX6366LKA46	MAX	mrc	$V_{TR} = 4.63 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} \le 50 \text{ mKA}$	SOT23-8	RESET • CE IN • GND • WDI • VCC • OUT • BATT • CE OUT
AABA	MAX6366LKA44	MAX	mrc	$V_{TR} = 4.38 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} \le 50 \text{ mKA}$	SOT23-8	RESET ◆ CE IN ◆ GND ◆ WDI ◆ VCC ◆ CUT ◆ BATT ◆ CE CUT
AABB	MAX6366LKA31	MAX	mrc	$V_{TR} = 3.08 \text{B}; V_{DO} = 1.25.5 \text{B}; I_{CC} < 50 \text{mrA}$	SOT23-8	RESET • CE IN • GND • WDI • VCC • CUT • BATT • CE CUT
AABC	MAX6366LKA29	MAX	mrc	$V_{TR} = 2.93 \text{B}; V_{DO} = 1.25.5 \text{B}; I_{CC} < 50 \text{mKA}$	SOT23-8	RESET • CE IN • GND • WDI • VCC • CUT • BATT • CE CUT
AABD	MAX6366LKA26	MAX	mrc	$V_{TR} = 2.63B$; $V_{DO} = 1.25.5B$; $I_{CC} < 50$ MKA	SOT23-8	RESET • CE IN • GND • WDI • VCC • OUT • BATT • CE OUT
AABE	MAX6366LKA23	MAX	mrc	$V_{TR} = 2.32B$; $V_{DO} = 1.25.5B$; $I_{CC} < 50$ mKA	SOT23-8	RESET • CE IN • GND • WDI • VCC • OUT • BATT • CE OUT
AABF	MAX6366PKA46	MAX	mrc	$V_{TR} = 4.63 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 50 \text{ mKA}$	SOT23-8	RESET • CE IN • GND • WDI • VCC • OUT • BATT • CE OUT
AABG	MAX6366PKA44	MAX	mrc	$V_{TR} = 4.38B$; $V_{DO} = 1.25.5B$; $I_{CC} < 50$ MKA	SOT23-8	RESET • CE IN • GND • WDI • VCC • OUT • BATT • CE OUT
AABH	MAX6366PKA31	MAX	mrc	$V_{TB} = 3.08B$; $V_{DO} = 1.25.5B$; $I_{CC} \le 50$ mKA	SOT23-8	RESET ◆CE IN ◆ GND ◆ WDI ◆ VCC ◆ OUT ◆ BATT ◆ CE OUT
AABI	MAX6366PKA29	MAX	mrc	$V_{TR} = 2.93B$; $V_{DO} = 1.25.5B$; $I_{CC} < 50 \text{ MKA}$	SOT23-8	RESET • CE IN • GND • WDI • VCC • OUT • BATT • CE OUT
AABJ	MAX6366PKA26	MAX	mrc	$V_{TR} = 2.63 \text{B}; V_{DO} = 1.25.5 \text{B}; I_{CC} < 50 \text{me/s}$	SOT23-8	RESET • CE IN • GND • WDI • VCC • OUT • BATT • CE OUT
AABK	MAX6366PKA23	MAX	mrc	$V_{TR} = 2.32B$; $V_{00} = 1.25.5B$; $I_{CC} < 50$ mKA	SOT23-8	RESET • CE IN • GND • WDI • VCC • OUT • BATT • CE OUT
AABL	MAX6366HKA46	MAX	mrc	V _{TR} = 4.63 B; V _{DO} = 1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • WDI • VCC • OUT • BATT • CE OUT
AABM	MAX6366HKA44	MAX	mrc	$V_{TR} = 4.38B$; $V_{DO} = 1.25.5B$; $I_{CC} < 50 \text{ MKA}$	SOT23-8	RESET ◆CE IN ◆ GND ◆ WDI ◆ VCC ◆ OUT ◆ BATT ◆ CE OUT
AABN	MAX6366HKA31	MAX	mrc	$V_{TR} = 3.08B$; $V_{DO} = 1.25.5B$; $I_{CC} < 50$ mKA	SOT23-8	RESET ◆CE IN ◆ GND ◆ WDI ◆ VCC ◆ OUT ◆ BATT ◆ CE OUT
AABO	MAX6366HKA29	MAX	mrc	$V_{TR} = 2.93B$; $V_{DO} = 1.25.5B$; $I_{CC} \le 50$ mKA	SOT23-8	RESET ◆CE IN ◆GND ◆WDI ◆VCC ◆ OUT ◆ BATT ◆ CE OUT
AABP	MAX6366HKA26	MAX	mrc	$V_{TR} = 2.63B$; $V_{DO} = 1.25.5B$; $I_{CC} < 50$ mKA	SOT23-8	RESET • CE IN • GND • WDI • VCC • OUT • BATT • CE OUT
AABQ	MAX6366HKA23	MAX	mrc	V _{TR} = 2.32B; V _{DO} = 1.25.5B; I _{CC} < 50 mKA	SOT23-8	RESET • CE IN • GND • WDI • VCC • OUT • BATT • CE OUT
AABR	MAX6367LKA46	MAX	mrc	V _{TR} = 4.63B; V _{DO} = 1.25.5B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • BATT ON • VCC • OUT • BATT • CE OUT
AABS	MAX6367LKA44	MAX	mrc	$V_{TR} = 4.38B$; $V_{DO} = 1.25.5B$; $I_{CC} < 50$ mKA	SOT23-8	RESET • CE IN • GND • BATT ON • VCC • OUT • BATT • CE OUT
AABT	MAX6367LKA31	MAX	mrc	$V_{TR} = 3.08B$; $V_{DO} = 1.25.5B$; $I_{CC} < 50$ mKA	SOT23-8	RESET •CEIN • GND • BATT ON • VCC • OUT • BATT •CE OUT
AABU	MAX6367LKA29	MAX	mrc	$V_{TR} = 2.93B$; $V_{DO} = 1.25.5B$; $I_{CC} < 50$ MKA	SOT23-8	RESET ◆CE IN ◆GND ◆BATT ON ◆VCC ◆ OUT ◆BATT ◆CE OUT
AABV	MAX6367LKA26	MAX	mrc	$V_{TR} = 2.63 B$; $V_{DO} = 1.25.5 B$; $I_{CC} < 50 \text{ mKA}$	SOT23-8	RESET ◆ CE IN ◆ GND ◆ BATT ON ◆ VCC ◆ OUT ◆ BATT ◆ CE OUT
AABW	MAX6367LKA23	MAX	mrc	$V_{TR} = 2.32 B$; $V_{DO} = 1.25.5 B$; $I_{CC} < 50 \text{ mKA}$	SOT23-8	RESET ◆CE IN ◆ GND ◆ BATT ON ◆ VCC ◆ OUT ◆ BATT ◆ CE OUT
AABX	MAX6367PKA46	MAX	mrc	$V_{TR} = 4.63 B$; $V_{DO} = 1.25.5 B$; $I_{CC} < 50 \text{ mKA}$	SOT23-8	RESET • CE IN • GND • BATT ON • VCC • OUT • BATT • CE OUT
AABY	MAX6367PKA44	MAX	mrc	$V_{TR} = 4.38 B$; $V_{DO} = 1.25.5 B$; $I_{CC} < 50 \text{ mKA}$	SOT23-8	RESET ◆ CE IN ◆ GND ◆ BATT ON ◆ VCC ◆ OUT ◆ BATT ◆ CE OUT
AABZ	MAX6367PKA31	MAX	mrc	$V_{TR} = 3.08 \text{B}; V_{DO} = 1.25.5 \text{B}; I_{CC} < 50 \text{mikA}$	SOT23-8	RESET ◆ CE IN ◆ GND ◆ BATT ON ◆ VCC ◆ OUT ◆ BATT ◆ CE OUT
AACA	MAX6367PKA29	MAX	mrc	$V_{TR} = 2.93 \text{B}; V_{DO} = 1.25.5 \text{B}; I_{CC} \le 50 \text{mkA}$	SOT23-8	RESET • CE IN • GND • BATT ON • VCC • OUT • BATT • CE OUT
AACB	MAX6367PKA26	MAX	mrc	$V_{TR} = 2.63 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 50 \text{ mKA}$	SOT23-8	RESET • CE IN • GND • BATT ON • VCC • OUT • BATT • CE OUT





Код	Типономинал	5	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
AACC	MAX6367PKA23	MAX	mrc	V _{TR} = 2.32 B; V _{DD} = 1.25.5 B; I _{CC} < 50 mKA	SOT23-8	RESET • CE IN • GND • BATT ON • VCC • OUT • BATT • CE OUT
AACD	MAX6367HKA46	MAX	mrc	V _{TR} = 4.63 B; V _{DD} = 1.25.5 B; I _{CC} < 50 mkA	SOT23-8	RESET • CE IN • GND • BATT ON • VCC • OUT • BATT • CE OUT
AACE	MAX6367HKA44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • BATT ON • VCC • OUT • BATT • CE OUT
AACF	MAX6367HKA31	MAX	mrc	$V_{TR} = 3.08 \text{ B}; V_{DD} = 1.25.5 \text{ B}; I_{CC} < 50 \text{ mKA}$	SOT23-8	RESET • CE IN • GND • BATT ON • VCC • OUT • BATT • CE OUT
AACG	MAX6367HKA29	MAX	mrc	V _{TR} =2.93 B; V _{DD} =1.25.5 B; I _{CC} < 50 mKA	SOT23-8	RESET • CE IN • GND • BATT ON • VCC • OUT • BATT • CE OUT
AACH	MAX6367HKA26	MAX	mrc	V _{TR} =2.63 B; V _{DD} =1.25.5 B; I _{CC} < 50 mKA	SOT23-8	RESET • CE IN • GND • BATT ON • VCC • OUT • BATT • CE OUT
AACI	MAX6367HKA23	MAX	mrc	V _{TR} = 2.32 B; V _{DD} = 1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • BATT ON • VCC • OUT • BATT • CE OUT
AACJ	MAX6368LKA46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACK	MAX6368LKA44	MAX	mrc	V _{TB} =4.38 B; V _{DD} =1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACL	MAX6368LKA31	MAX	mrc	V _{TR} =3.08 B; V _{DD} =1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACM	MAX6368LKA29	MAX	mrc	V _{TR} = 2.93 B; V _{DD} = 1.25.5 B; I _{CC} < 50 mkA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACN	MAX6368LKA26	MAX	mrc	V _{TR} =2.63 B; V _{DD} =1.25.5 B; I _{CC} < 50 mKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACO	MAX6368LKA23	MAX	mrc	V _{TR} = 2.32 B; V _{DD} = 1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACP	MAX6368PKA46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACQ	MAX6368PKA44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25.5 B; I _{CC} < 50 mKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACR	MAX6368PKA31	MAX	mrc	V _{TR} =3.08 B; V _{DD} =1.25.5 B; I _{CC} < 50 mKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACS	MAX6368PKA29	MAX	mrc	V _{TR} =2.93 B; V _{DD} =1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACT	MAX6368PKA26	MAX	mrc	V _{TR} =2.63 B; V _{DD} =1.25.5 B; I _{CC} < 50 мкА	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACU	MAX6368PKA23	MAX	mrc	V _{TR} =2.32 B; V _{DD} =1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACV	MAX6368HKA46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACW	MAX6368HKA44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACX	MAX6368HKA31	MAX	mrc	V _{TR} = 3.08 B; V _{DD} = 1.2 5.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACY	MAX6368HKA29	MAX	mrc	V _{TR} =2.93 B; V _{DD} =1.25.5 B; I _{CC} < 50 mkA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AACZ	MAX6368HKA26	MAX	mrc	V _{TR} = 2.63 B; V _{DD} = 1.2., 5.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AADA	MAX6368HKA23	MAX	mrc	V _{TR} = 2.32 B; V _{DO} = 1.2 5.5 B; I _{CC} < 50 MKA	SOT23-8	RESET • CE IN • GND • RESET IN • VCC • OUT • BATT • CE OUT
AADB	MAX4491AKA	MAX	dOA	R-R; V _{DD} = 2.75.5/±1.35±2.75B; f _{BD} = 10MFu; V _{DS} < 16 мB	SOT23-8	OUTA • INA- • INA+ • VSS • INB+ • INB- • OUTB • VDD
AADC	MAX6369KA	MAX	wdt	t _{STUP} =0.00160 c; V _{DD} =2.55.5B; I _{CC} <20 мкA	SOT23-8	WDI • GND • n.c. • SET0 • SET1 • SET2 • WDO • VCC
AADD	MAX6370KA	MAX	wdt	t _{STUP} =0.00160 c; V _{DD} =2.55.5B; I _{DC} < 20 MKA	SOT23-8	WDI • GND • n.c. • SET0 • SET1 • SET2 • WDO • VCC
AADE	MAX6371KA	MAX	wdt	t _{STUP} =60 с; V _{DD} =2.55.5B; I _{CC} <20мкА	SOT23-8	WDI • GND • n.c. • SET0 • SET1 • SET2 • WDO • VCC



MSOP-8 SOT23-8 SOP-8 TSOT23-8



0 MSOP-10

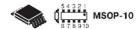
Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
AADF	MAX6372KA	MAX	wdt	t _{STUP} =60c; V _{DO} =2.55.5B; I _{CC} <20mkA	SOT23-8	WDI • GND • n.c. • SET0 • SET1 • SET2 • WDO • VCC
AADG	MAX6373KA	MAX	wdt	$t_{STUP} = 0.000260 c; V_{DD} = 2.55.5 B; I_{CC} < 20 mkA$	SOT23-8	WDI • GND • n.c. • SET0 • SET1 • SET2 • WDO • VCC
AADH	MAX6374KA	MAX	wdt	$t_{STUP} = 0.000260 c; V_{DO} = 2.55.5 B; I_{CC} < 20 mkA$	SOT23-8	WDI • GND • n.c. • SET0 • SET1 • SET2 • WDO • VCC
AADI	MAX4402AKA	MAX	dOA	R-R; V_{DD} =2.55.5B; f_{BD} =800 k Γ u; V_{OSI} <5.5 mB	SOT23-8	OUTA • INA- • INA+ • VSS • INB+ • INB- • OUTB • VCC
AADK	MAX3314KA	MAX	trans	RS-232; V _{CC} = ±4.75±5.25 B; f _{DR} = 460 Кбит/с; I _{CC} < 100 мкА	SOT23-8	VCC • SHDN • ROUT • TIN • TOUT • RIN • V- • GND
AADL	MAX3314EKA	MAX	trans	RS-232; V _{CC} = ±4.75±5.25 B; f _{DR} = 460 Кбит/с; I _{CC} < 100 мкА	SOT23-8	VCC • SHDN • ROUT • TIN • TOUT • RIN • V- • GND
AADM	MAX1801EKA	MAX	dodo	$V_{IN} = 2.75.5 \text{ B}; V_{REF} = 1.25 \text{ B}; I_{CC} < 300 \text{ mKA}$	SOT23-8	OSC • GND • REF • DCON • COMP • FB • IN • DL
AADN	MAX9110EKA	MAX	LVDS drv	V _{OD} =350 mB; V _{CC} = 33.6 B; I _{CC} < 8 mA	SOT23-8	DIN • GND • n.c. • VCC • n.c. • n.c. • DO+ • DO-
AADO	MAX9112EKA	MAX	LVDS drv x2	V _{OD} =350 MB; V _{CC} =33.6B; I _{CC} <13 MA	SOT23-8	DIN1 • GND • DIN2 • VCC • DO2- • DO2+ • DO1+ • DO1-
AADR	MAX4413EKA	MAX	dOA	R-R; V ₀₀ =2.75.5 B; f ₈₀ =500МГц; V _{0SI} <9 мВ	SOT23-8	OUTA • INA- • INA+ • VEE • INB+ • INB- • OUTB • VCC
AADS	MAX4453EKA	MAX	dOA	R-R; V _{DD} = 2.75.25 B; f _{BD} = 200 MFu; V _{DSI} < 12 MB	SOT23-8	OUTA • INA- • INA+ • VEE • INB+ • INB- • OUTB • VCC
AADT	MAX4353EKA	MAX	dOA	R-R; V _{DD} = 2.75.25 B; f _{BD} = 80 МГц; V _{DSI} < 12 мВ	SOT23-8	OUTA • INA- • INA+ • VEE • INB+ • INB- • OUTB • VCC
AADU	MAX1115EKA	MAX	ADC	8-pasp.; SPI/QSPI/Microwire; V ₀₀ = 2.73.6 B	SOT23-8	VDD • CH0 • i.c. • GND • i.c. • CONVST • DOUT • SCLK
AADV	MAX1116EKA	MAX	ADC	8-pasp.; SPI/QSPI/Microwire; V _{DD} = 4.55.5 B	SOT23-8	VDD • CH0 • i.c. • GND • i.c. • CONVST • DOUT • SCLK
AADW	MAX1117EKA	MAX	ADC	2x8-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.73.6 B	SOT23-8	VDD • CH0 • CH1 • GND • (REF) i.c. • CNVST • DOUT • SCLK
AADX	MAX1118EKA	MAX	ADC	2x8-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.75.5 B	SOT23-8	VDD • CH0 • CH1 • GND • (REF) i.c. • CNVST • DOUT • SCLK
AADY	MAX1119EKA	MAX	ADC	2x8-pasp.; SPI/QSPI/Microwire; V _{DD} =4.55.5 B	SOT23-8	VDD • CH0 • CH1 • GND • (REF) i.c. • CNVST • DOUT • SCLK
AADZ	MAX989EKA	MAX	cmp x2	R-R; V _{CSI} <±7 mB; V _{CC} = 2.55.5 B; I _{CC} < 48 mkA	SOT23-8	OUTA • INA • • INA • • VEE • INB • • INB • • OUTB • VCC
AAEA	MAX990EKA	MAX	cmp x2	R-R; V _{CS} <±7 mB; V _{CC} = 2.55.5 B; I _{CC} < 48 mkA	SOT23-8	OUTA • INA- • INA+ • VEE • INB+ • INB- • OUTB • VCC
AAEB	MAX991EKA	MAX	cmp x2	P-R; V _{CS} < ±7 mB; V _{CC} = 2.55.5 B; I _{CC} < 190 mcA	SOT23-8	CUTA • INA- • INA+ • VEE • INB+ • INB- • CUTB • VCC
AAEC	MAX992EKA	MAX	cmp x2	R-R; V _{CS} < ±7 mB; V _{CC} = 2.55.5 B; I _{CC} < 190 mkA	SOT23-8	OUTA • INA- • INA+ • VEE • INB+ • INB- • OUTB • VCC
AAED	MAX9113EKA	MAX	LVDS drv x2	$V_{DH} > 2.7B$; $V_{DL} < 0.4B$; $V_{CC} = 33.6B$; $I_{CC} < 11$ MA	SOT23-8	VCC • GND • OUT1 • OUT2 • IN2- • IN2+ • IN1+ • IN1-
AAEE	MAX9111EKA	MAX	LVDS	V _{DH} >2.7B; V _{DL} < 0.4B; V _{CC} = 33.6B; I _{CC} < 6 MA	SOT23-8	VCC • GND • OUT • n.c. • n.c. • n.c. • IN+ • IN1-
AAEF	MAX9032AKA	MAX	cmp x2	R-R; V _{OSI} < ±5 MB; V _{DO} = 2.55.5 B; I _{DO} < 110 MKA	SOT23-8	OUTA • INA- • INA+ • VSS • INB+ • INB- • OUTB • VDD
AAEG	MAX9022AKA	MAX	cmp x2	R-R; V _{CSI} < ±8 mB; V _{DO} = 2.55.5 B; I _{DO} < 10 mKA	SOT23-8	OUTA • INA- • INA+ • VSS • INB+ • INB- • OUTB • VDD
AAEI	MAX4564EKA	MAX	asw	SPDT; R _{DN} < 100 OM; V _{DD} = 1.812/±1.8±6 B	SOT23-8	NC • V+ • IN • NO • GND • V- • EN • COM
AAEJ	MAX4482AKA	MAX	dOA	R-R; V _{DD} =2.55.5 B; I _{CC} < 100 mKA; V _{DS} < 5.5 mB	SOT23-8	OUTA • INA- • INA+ • VSS • INB+ • INB- • OUTB • VDD
AAEK	MAX4471EKA	MAX	dOA	R-R; V _{DD} = 1.85.5 B; f _{BD} = 9 κΓц; I _{CD} < 1.2 мкA; V _{DSI} < 7 мВ	SOT23-8	OUTA ◆INA- ◆INA+ ◆VSS ◆INB+ ◆INB- ◆ OUTB ◆VCC
AAEL	MAX4474EKA	MAX	dOA	R-R; V _{DD} = 1.85.5 B; f _{BD} = 40 κΓι; I _{DD} < 1.2 мкA; V _{DSI} < 7 мB	SOT23-8	OUTA • INA- • INA+ • VSS • INB+ • INB- • OUTB • VCC

MSOP-10 (578910)

US-8 SOT23-8 MSOP-8 TSOT23-8 SOP-8







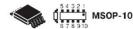
Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
AAFR	MAX6706YKA	MAX	mrc + wdt	$V_{TR} = 2.19B$; $V_{00} = 1.25.5B$; $I_{CC} < 20 \text{ MKA}$	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • WDO
AAFS	MAX6706ZKA	MAX	mrc + wdt	$V_{TR} = 2.32 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ mkA}$	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • WDO
AAFU	MAX6707MKA	MAX	mrc + wdt	$V_{TR} = 4.38 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ MKA}$	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • WDO
AAFV	MAX6707RKA	MAX	mrc + wdt	$V_{TR} = 2.63 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ mrA}$	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • WDO
AAFW	MAX6707SKA	MAX	mrc + wdt	$V_{TR} = 2.93 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ mKA}$	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • WDO
AAFX	MAX6707TKA	MAX	mrc + wdt	$V_{TR} = 3.08B$; $V_{DO} = 1.25.5B$; $I_{CC} < 20 \text{ mkA}$	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • WDO
AAFY	MAX6707YKA	MAX	mrc + wdt	$V_{TR} = 2.19B$; $V_{DO} = 1.25.5B$; $I_{CC} < 20 \text{ mrA}$	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • WDO
AAFZ	MAX6707ZKA	MAX	mrc + wdt	$V_{TR} = 2.32 \mathrm{B}; V_{DO} = 1.25.5 \mathrm{B}; I_{CC} < 20 \mathrm{mkA}$	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • WDO
AAGA	MAX6708LKA	MAX	mrc + wdt	$V_{TR} = 4.63 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ MiKA}$	SOT23-8	MR • VCC • GND • PFI • PFO • n.c. • RESET • RESET
AAGB	MAX6708MKA	MAX	mrc + wdt	$V_{TR} = 4.38 \text{B}; V_{DO} = 1.25.5 \text{B}; I_{CC} < 20 \text{mKA}$	SOT23-8	MR • VCC • GND • PFI • PFO • n.c. • RESET • RESET.
AAGC	MAX6708RKA	MAX	mrc + wdt	$V_{TR} = 2.63 \mathrm{B}; V_{DO} = 1.25.5 \mathrm{B}; I_{CC} < 20 \mathrm{mkA}$	SOT23-8	MR • VCC • GND • PFI • PFO • n.c. • RESET • RESET
AAGD	MAX6708SKA	MAX	mrc + wdt	$V_{TR} = 2.93 \text{B}; V_{DO} = 1.25.5 \text{B}; I_{CC} < 20 \text{mrA}$	SOT23-8	MR • VCC • GND • PFI • PFO • n.c. • RESET • RESET
AAGE	MAX6708TKA	MAX	mrc + wdt	$V_{TR} = 3.08 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ m/s}A$	SOT23-8	MR • VCC • GND • PFI • PFO • n.c. • RESET • RESET
AAGF	MAX6708YKA	MAX	mrc + wdt	$V_{TR} = 2.19B$; $V_{DO} = 1.25.5B$; $I_{CC} < 20 \text{ MiKA}$	SOT23-8	MR • VCC • GND • PFI • PFO • n.c. • RESET • RESET
AAGG	MAX6708ZKA	MAX	mrc + wdt	$V_{1R} = 2.32B$; $V_{00} = 1.25.5B$; $I_{CC} < 20 \text{ m/sA}$	SOT23-8	MR • VCC • GND • PFI • PFO • n.c. • RESET • RESET
AAGH	MAX6701LKA	MAX	mrc + wdt	$V_{TR} = 4.63 \mathrm{B}; V_{DO} = 1.25.5 \mathrm{B}; I_{CC} < 20 \mathrm{micA}$	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGI	MAX6701MKA	MAX	mrc + wdt	$V_{TR} = 4.38 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ m/s}A$	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGJ	MAX6701RKA	MAX	mrc + wdt	$V_{TR} = 2.63 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ m/s}A$	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGK	MAX6701SKA	MAX	mrc + wdt	$V_{TR} = 2.93 B$; $V_{DO} = 1.25.5 B$; $I_{CC} < 20 \text{ mix}A$	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGL	MAX6701TKA	MAX	mrc + wdt	$V_{TR} = 3.08 \text{B}; V_{DO} = 1.25.5 \text{B}; I_{CC} < 20 \text{mikA}$	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGM	MAX6701YKA	MAX	mrc + wdt	$V_{TR} = 2.19B$; $V_{DO} = 1.25.5B$; $I_{CC} < 20 \text{ m/sA}$	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGN	MAX6701ZKA	MAX	mrc + wdt	$V_{TR} = 2.32B$; $V_{DO} = 1.25.5B$; $I_{CC} < 20 \text{ MiKA}$	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGO	MAX6702LKA	MAX	mrc + wdt	$V_{TR} = 4.63 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ MKA}$	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGP	MAX6702MKA	MAX	mrc + wdt	V _{TR} = 4.38 B; V _{DO} = 1.25.5 B; I _{CC} < 20 mKA	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGQ	MAX6702RKA	MAX	mrc + wdt	V _{TR} = 2.63 B; V _{DO} = 1.25.5 B; I _{CC} < 20 MKA	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGR	MAX6702SKA	MAX	mrc + wdt	$V_{TR} = 2.93B$; $V_{DO} = 1.25.5B$; $I_{CC} < 20 \text{ m/kA}$	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGS	MAX6702TKA	MAX	mrc + wdt	$V_{TR} = 3.08 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ m/kA}$	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGT	MAX6702YKA	MAX	mrc + wdt	V _{TR} = 2.19B; V _{DD} = 1.25.5B; I _{CC} < 20 мкA	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGU	MAX6702ZKA	MAX	mrc+	V _{TR} = 2.32B; V _{DO} = 1.25.5B; I _{CC} < 20 MIKA	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO

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Код	Типономинал	5	ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
AAGV	MAX6703LKA	MAX	mrc + wdt	$V_{TR} = 4.63 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ MKA}$	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGW	MAX6703MKA	MAX	mrc + wdt	V _{TR} = 4.38 B; V _{DO} = 1.25.5 B; I _{CC} < 20 mkA	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGX	MAX6703RKA	MAX	mrc + wdt	$V_{TR} = 2.63 \text{ B}, V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ mkA}$	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGY	MAX6703SKA	MAX	mrc + wdt	$V_{TR} = 2.93 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ mKA}$	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAGZ	MAX6703TKA	MAX	mrc + wdt	V _{TR} = 3.08 B; V _{DD} = 1.25.5 B; I _{CC} < 20 MKA	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAHA	MAX6703YKA	MAX	mrc + wdt	V _{TR} =2.19 B; V _{DD} =1.25.5 B; I _{CC} < 20 MKA	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAHB	MAX6703ZKA	MAX	mrc + wdt	$V_{TR} = 2.32 \text{ B}; V_{DD} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ MKA}$	SOT23-8	MR • VCC • GND • RST_IN1 • RST_IN2 • WDI • RESET • WDO
AAHC	MAX6704LKA	MAX	mrc + wdt	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} < 20 MKA	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • RESET
AAHD	MAX6704MKA	MAX	mrc + wdt	V _{TR} =4.38 B; V _{DD} =1.25.5 B; I _{CC} < 20 mkA	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • RESET
AAHE	MAX6704RKA	MAX	mrc + wdt	V _{TR} = 2.63 B; V _{DD} = 1.25.5 B; I _{CC} < 20 mkA	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • RESET
AAHF	MAX6704SKA	MAX	mrc + wdt	V _{TR} = 2.93 B; V _{DO} = 1.25.5 B; I _{CC} < 20 mkA	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • RESET
AAHG	MAX6704TKA	MAX	mrc + wdt	$V_{TR} = 3.08 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ mKA}$	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • RESET
AAHG	MAX9052AEUA	MAX	cmp x2 + vref	$\begin{array}{l} \text{R-R; V}_{DSI}\!<\!\pm\!7\text{mB; V}_{CC}\!=\!2.75.5\text{B;}\\ \text{V}_{REF}\!=\!2.500\text{B; I}_{CC}\!<\!72\text{micA} \end{array}$	MSOP-8	OUTA • REF • INA+ • VEE • INB+ • INB- • OUTB • VCC
AAHH	MAX6704YKA	MAX	mrc + wdt	$V_{TR} = 2.19 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 20 \text{ MKA}$	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • RESET
AAHI	MAX6704ZKA	MAX	mrc + wdt	$V_{TR} = 2.32 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} \le 20 \text{ mkA}$	SOT23-8	MR • VCC • GND • PFI • PFO • WDI • RESET • RESET
AAHI	MAX9052BEUA	MAX	cmp x2 + vref	$\begin{array}{l} \text{R-R; V}_{OSI} \!<\! \pm \! 7 \text{mB; V}_{CC} \!=\! 2.75.5 \text{B;} \\ \text{V}_{REF} \!=\! 2.500 \text{B; I}_{CC} \!<\! 72 \text{micA} \end{array}$	MSOP-8	OUTA • REF • INA+ • VEE • INB+ • INB- • OUTB • VCC
AAHJ	MAX6391KA46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} < 25 MKA	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • R1
AAHK	MAX6391KA44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25.5 B; I _{CC} < 25 mkA	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • R1
AAHL	MAX6391KA31	MAX	mrc	V _{TR} = 3.08 B; V _{DO} = 1.25.5 B; I _{CC} < 25 mkA	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • R1
AAHM	MAX6391KA29	MAX	mrc	V _{TR} =2.93 B; V _{DO} =1.25.5 B; I _{CC} < 25 mkA	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • R1
AAHN	MAX6391KA26	MAX	mrc	V _{TR} = 2.63 B; V _{DO} = 1.25.5 B; I _{CC} < 25 mkA	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • R1
AAHO	MAX6391KA23	MAX	mrc	V _{TR} =2.32 B; V _{DO} =1.25.5 B; I _{CC} < 25 mkA	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • R1
AAHP	MAX6391KA22	MAX	mrc	V _{TR} =2.19 B; V _{DO} =1.25.5 B; I _{CC} < 25 mkA	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • R1
AAHQ	MAX6391KA17	MAX	mrc	$V_{TR} = 1.67 \text{B}; V_{DO} = 1.25.5 \text{B}; I_{CC} < 25 \text{mkA}$	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • R1
AAHR	MAX6391KA16	MAX	mrc	V _{TR} =1.58 B; V _{DD} =1.25.5 B; I _{CC} < 25 MKA	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • R1
AAHS	MAX6392KA46	MAX	mrc	V _{TR} =4.63 B; V _{DD} =1.25.5 B; I _{CC} < 25 mkA	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • MR
AAHT	MAX6392KA44	MAX	mrc	V _{TR} =4.38 B; V _{DD} =1.25.5 B; I _{CC} <25 mkA	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • MR
AAHU	MAX6392KA31	MAX	mrc	V _{TR} =3.08 B; V _{DD} =1.25.5 B; I _{CC} < 25 mkA	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • MR





Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
AAHV	MAX6392KA29	MAX	mrc	$V_{TR} = 2.93 B$; $V_{DO} = 1.25.5 B$; $I_{CC} \le 25 \text{ mKA}$	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • MR
WHAA	MAX6392KA26	MAX	mrc	$V_{TR} = 2.63B$; $V_{DO} = 1.25.5B$; $I_{CC} \le 25 \text{ MKA}$	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • MR
AAHX	MAX6392KA23	MAX	mrc	$V_{TR} = 2.32B$; $V_{DO} = 1.25.5B$; $I_{CC} \le 25 \text{ MKA}$	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • MR
AAHY	MAX6392KA22	MAX	mrc	$V_{TR} = 2.19B$; $V_{DO} = 1.25.5B$; $I_{CC} \le 25 \text{ MKA}$	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • MR
AAHZ	MAX6392KA17	MAX	mrc	V _{TR} = 1.67B; V _{DD} = 1.25.5B; I _{CC} < 25 mkA	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • MR
AAIA	MAX6392KA16	MAX	mrc	$V_{TR} = 1.58B$; $V_{DO} = 1.25.5B$; $I_{CC} < 25 \text{ mkA}$	SOT23-8	RESET IN2 • VCC • CSRT • GND • RESET2 • R2 • RESET1 • MR
AAIB	MAX9107EKA	MAX	cmp x2	V _{OSI} < 4 MB; V _{CC} = 4.55.5 B; I _{CC} < 1.4 MA	SOT23-8	OUTA • INA- • INA+ • GND • INB+ • INB- • OUTB • VCC
AAIC	MAX4351EKA	MAX	dOA	R-R; V _{DD} =±4.5±5.5 B; f _{BD} =210 MFu; V _{OSI} <26 MB	SOT23-8	OUTA • INA- • INA+ • VEE • INB+ • INB- • OUTB • VCC
AAID	MAX5407EKA	MAX	Dpot	32 позиции; логарифм.; 20 кОм; V _{DD} = 2.75.5 В	SOT23-8	H•GND•W•L•U/D•CS•VDD•ZCEN
AAIE	MAX4649EKA	MAX	asw	SPDT; R _{DN} < 60 OM; V _{DD} = 936/±4.5±20 B	SOT23-8	COM • NC • GND • V+ • n.c. • IN • V- • NO
ABA	AD8602ARM	AD	dOA	$f_{BO} = 8 \text{ MFu}; P_D = 12 \text{ MBT}, V_{DO} = 2.75.5 \text{ B}$	MSOP-8	OUT A • -IN A • +IN A • V- • +IN B • -IN B • OUT B • V+
ABD	AD8602DRM	AD	dOA	$f_{BO} = 8 \text{ MFu}; P_D = 12 \text{ MBT}; V_{DO} = 2.75.5 \text{ B}$	MSOP-8	OUT A • -IN A • +IN A • V- • +IN B • -IN B • OUT B • V+
AFA	AD8527ARM	AD	dOA	$f_{BO} = 7 \text{ MFu}; P_D = 12 \text{ MBT}; V_{DO} = 1.86 \text{ B}$	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
AGA	AD8632ARM	AD	dOA	$f_{BD} = 5 \text{ MFu}; P_D = 6 \text{ MBT}; V_{DD} = 1.86 \text{ B}$	MSOP-8	OUT A • -IN A • +IN A • V- • +IN B • -IN B • OUT B • V+
AHA	AD8551ARM	AD	OA	$f_{BD} = 1.5 \text{ MFu}, P_D = 5 \text{ MBT}, V_{DD} = 2.75.5 \text{ B}$	MSOP-8	n.c. • -IN A • +IN A • V - • n.c. • OUT A • V + • n.c.
AJA	AD8571ARM	AD	OA	$f_{BD} = 1.5 \text{ MFu}, P_D = 5 \text{ MBT}, V_{DD} = 2.75.5 \text{ B}$	MSOP-8	n.c. • -IN A • +IN A • V - • n.c. • OUT A • V + • n.c.
AK	SSM2250RM	AD	amp	$V_{CC} = 2.76 B_1 I_{CC} = 6.4 \text{MA};$ $P_{OUT} = 1.5 \text{BT} (\text{mono})/0.25 \text{BT} (\text{crepeo});$ $f_{BD} = 4 \text{MFu}$	MSOP-10	LIN • SHTDN • SE/BTL • GND • RIN • R OUT • BPS • BTL+ • VDD • L OUT/BTL-
AK#	SSM2250RMZ	AD	amp	$V_{CC} = 2.76 B; I_{CC} = 6.4 \text{ MA};$ $P_{OUT} = 1.5 B\tau \text{ (моно)/0.25 B}\tau \text{ (стерео)};$ $f_{BD} = 4 \text{ MFu}$	MSOP-10	LIN • SHTDN • SE/BTL • GND • RIN • R OUT • BPS • BTL+ • VDD • L OUT/BTL-
AKG	TLV2632IDGK	TI	dOA	R-R; V _{DD} =2.75.5 B; f _{BD} =9 MΓu; V _{DSI} <4.5 MB	MSOP-8	OUT1 • IN1 • IN1+ • GND • IN2+ • IN2 • OUT2 • VDD
AKK	TLV2633IDGS	TI	dOA	R-R; V _{DD} =2.75.5 В; f _{BD} =9 МГц; V _{OSI} <4.5 мВ	MSOP-10	OUT1 • IN1 • IN1+ • GND • SHDN1 • SHDN2 • IN2+ • IN2 • OUT2 • VDD
AND	OP162DRM	AD	OA	R-R; V _{DO} = 2.712 В; f _{BD} = 15 МГц; I _S = 850 мкА; V _{DSI} < 325 мкВ	MSOP-8	NULL • -IN • +IN • V- • n.c. • OUT • V+ • NULL
AOB	THS4130CDGN	TI	DA	V _{DD} =530/2.5±15 B; f _{BD} = 150 МГц; V _{OSI} < 3 мВ	MSOPPo werPAD-8	VIN • VOCM • VCC+ • VOUT+ • VOUT • VCC • PD • VIN+
AOC	THS4130IDGN	TI	DA	V _{DD} =530/2.5±15В; f _{BD} = 150 МГц; V _{OSI} < 3 мВ	MSOPPo werPAD-8	VIN • VOCM • VCC+ • VOUT+ • VOUT • VCC • PD • VIN+
AOD	THS4131CDGN	П	DA	V _{DD} =530/2.5±15В; f _{BD} = 150 МГц; V _{OSI} < 3 мВ	MSOPPo werPAD-8	VIN • VOCM • VCC+ • VOUT+ • VOUT • VCC • n.c. • VIN+
AOE	THS4131IDGN	П	DA	V _{DD} =530/2.5±15B; f _{BD} =150 МГц; V _{OSI} <3 мВ	MSOPPo werPAD-8	VIN • VOCM • VCC+ • VOUT+ • VOUT • VCC • n.c. • VIN+
AOF	THS4140CDGN	П	DA	V _{DD} =530/2.5±15B; f _{BD} =160 МГц; V _{OSI} <8.5 мВ	MSOPPo werPAD-8	VIN • VOCM • VCC+ • VOUT+ • VOUT • VCC • PD • VIN+
AOG	THS4140IDGN	TI	DA	V _{DD} =530/2.5±15В; f _{BD} =160МГц; V _{DSI} <8.5мВ	MSOPPo werPAD-8	VIN • VOCM • VCC+ • VOUT+ • VOUT • VCC • PD • VIN+
AOI	THS4141CDGN	П	DA	V _{DD} =530/2.5±15B; f _{BD} =160 MFu; V _{DSI} <8.5 MB	MSOPPo werPAD-8	VIN • VOCM • VCC+ • VOUT+ • VOUT • VCC • n.c. • VIN+
AOJ	OP162DRMZ	AD	OA	R-R; V _{DD} = 2.712 B; f _{BD} = 15 MFu; I _S = 850 mkA; V _{DSI} < 325 mkB	MSOP-8	NULL • -IN • +IN • V- • n.c. • OUT • V+ • NULL
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MSOP-10 (5 4 3 2 1) (6 7 8 9 10)



Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
AOK	THS4141IDGN	TI	DA	V _{DD} =530/2.5±15 B; f _{BD} = 160 MFu; V _{DSI} < 8.5 mB	MSOPPo werPAD-8	VIN • VOCM • VCC+• VOUT+• VOUT • VCC • n.c. • VIN+
AQA	AD8592ARM	AD	dOA	$f_{BD} = 2.2 M \Gamma_{U_i} P_D = 14 MB T_i V_{DD} = 2.56 B$	MSOP-10	OUT A • -IN A • +IN A • V- • SDA • SDB • +IN B • -IN B • OUT B • V+
ARA	AD8532ARM	AD	dOA	$f_{BD} = 3M\Gamma_{II}; P_D = 12MB\tau; V_{DD} = 2.76B$	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
ASO	THS4130IDGK	TI	DA	V_{D0} = 530/2.5±15 B; f_{BD} = 150 MFu; V_{DSI} < 3 MB	MSOP-8	VIN • VOCM • VCC+• VOUT+• VOUT • VCC • PD • VIN+
ASP	THS4131IDGK	TI	DA	V_{DD} = 530/2.5±15 B; f_{BD} = 150 MF $_{\text{H}}$; V_{DSI} < 3 MB	MSOP-8	VIN • VOCM • VCC+ • VOUT+ • VOUT • VCC • n.c. • VIN+
ASQ	THS4140IDGK	TI	DA	V_{DD} = 530/2.5±15 B; f_{BD} = 160 MF $_{\text{H}}$; V_{DSI} < 8.5 mB	MSOP-8	VIN • VOCM • VCC+ • VOUT+ • VOUT • VCC • PD • VIN+
ASR	THS4141IDGK	TI	DA	V _{DD} =530/2.5±15 B; f _{BD} =160 MΓ _Ц ; V _{DSI} <8.5 мВ	MSOP-8	VIN • VOCM • VCC+ • VOUT+ • VOUT • VCC • n.c. • VIN+
ATA	AD8566ARM	AD	dOA	$f_{BD} = 5M\Gamma_{H}; P_{D} = 24mBT; V_{DD} = 4.516B$	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
ATA#	AD8566ARMZ	AD	dOA	$f_{BD} = 5 M \Gamma_{II}; P_D = 24 MB \tau; V_{DD} = 4.516 B$	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
ATP	THS4130CDGK	TI	DA	V_{DD} = 530/2.5±15 B; f_{BD} = 150 MF $_{4}$; V_{DS} < 3 MB	MSOP-8	VIN • VOCM • VCC+ • VOUT+ • VOUT • VCC • PD • VIN+
ATQ	THS4131CDGK	TI	DA	$V_{DO} = 530/2.5\pm 15 B$; $f_{BD} = 150 M\Gamma_{H}$; $V_{OS} < 3 MB$	MSOP-8	VIN • VOCM • VCC+ • VOUT+ • VOUT • VCC • n.c. • VIN+
ATR	THS4140CDGK	TI	DA	V _{DD} =530/2.5±15 B; f _{BD} =160 MΓ _U ; V _{DS} <8.5 MB	MSOP-8	VIN • VOCM • VCC+ • VOUT+ • VOUT • VCC • PD • VIN+
ATS	THS4141CDGK	TI	DA	V _{DD} =530/2.5±15 B; f _{BD} = 160 MFц; V _{DS} < 8.5 мB	MSOP-8	VIN • VOCM • VCC+ • VOUT+ • VOUT • VCC • n.c. • VIN+
AVA	AD8542ARM	AD	dOA	$f_{BD} = 1 M \Gamma_{II}; P_D = 0.6 MBT; V_{DD} = 2.75.5 B$	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
AZA	OP1177ARM	AD	OA	V _{DD} =±2.5±15 В; I _S =600 мкА; V _{DSI} <60 мкВ	MSOP-8	n.c. • -IN • +IN • V- • n.c. • OUT • V+ • n.c.
B03	OPA2703EA	TI	dOA	R-R; V_{DD} = 412/±2±6 B; f_{BD} = 1 MFu; I_S = 300 mrA; V_{DS} < ±0.75 mB	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
B04	OPA2704EA	TI	dOA	R-R; V_{DD} = 412/±2±6 B; f_{BD} = 3 MFu; I_S = 300 mKA; V_{DS} < ±0.75 mB	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
B05	OPA2705EA	TI	dOA	R-R; V _{DD} = 412/±2±6 B; f _{BD} = 1 MFu; I _S = 250 mkA; V _{DS} < ±5 mB	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
B0A	AD8610ARM	AD	OA	$f_{BD} = 25 M\Gamma u; P_D = 40 \text{ MBT}; V_{DD} = \pm 5 \pm 13 \text{ B}$	MSOP-8	NULL • -IN • +IN • V - • NULL • OUT • V+ • n.c.
B10	AD5220BRM-10	AD	Dpot	128 позиций; 10 кОм	MSOP-8	CLK • U/D • A1 • GND • W1 • B1 • CS • VDD
B100	AD5220BRM-100	AD	Dpot	128 позиций; 100 кОм	MSOP-8	CLK • U/D • A1 • GND • W1 • B1 • CS • VDD
B26	INA326	ВВ/П	IA	R-R; V _{OSI} = 100 mkB; V _{DO} = 2.75B	MSOP-8	R1 • VIN • VIN+ • V • R2 • VO • V+ • R1
B27	INA327	ВВ/П	IA	R-R; V _{OSI} = 100 мкВ; V _{DO} = 2.75 В; блокировка	MSOP-10	R1 • VIN • VIN+ • V • V+ • ENBL • R2 • VO • V+ • R1
B2A	OP2177ARM	AD	dOA	V _{DD} = ±2.5±15 В; I _S = 1.2 мА; V _{DS} < 60 мкВ	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
B 36	OPA2336EA	TI	dOA	R-R; V_{DD} = 2.35.5B; I_S = 85 mkA; V_{DS} < ± 125 mkB	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
B47	OPA2347EA	TI	dOA	R-R; V _{DD} = 2.35.5B; f _{BD} = 350 κΓι; I _S = 80 κκΑ; V _{DS} < 7 κΒ	SOT23-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
B 48	OPA2348AI	TI	dOA	R-R; V _{DD} = 2.15.5B; f _{BD} = 1 МГц; I _S = 150 мкА; V _{DS} < 6 мВ	SOT23-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
B4A	AD822ARM	AD	dOA	f_{UG} = 1.8 MFu; P_D = 50 mB τ ; V_{DD} = 336/±1.5±18 B	MSOP-8	OUT1 • -IN1 • +IN1 • V - • +IN2 • -IN2 • OUT2 • V+
B50	AD5220BRM-50	AD	Dpot	128 позиций; 50 кОм	MSOP-8	CLK • U/D • A1 • GND • W1 • B1 • CS • VDD
B6A	AD8606ARM	AD	dOA	$f_{BD} = 10 \text{ MFu}; P_D = 14 \text{ MBT}; V_{DD} = 2.75.5 \text{ B}$	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
B6A#	AD8606ARMZ	AD	dOA	f _{BD} = 10 MΓu; P _D = 14 мBт; V _{DO} = 2.75.5 B	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
B7A	AD8510ARM	AD	OA	f _{BD} = 8МГц; P _D = 70 мВт; V _{DO} = ±5±15 В	MSOP-8	n.c. • -IN • +IN • V- • n.c. • OUT • V+ • n.c.





Код	Типономинал	6	Φ	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
B8A	AD8512ARM	AD	dOA	f _{BO} = 8 MFц; P _O = 70 мВт; V _{DO} = ±5±15 В	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
BHK	OPA2363AI	TI	dOA	R-R; V_{DD} = 1.85.5 B; f_{BD} = 7 MFu; I_S = 1.4 mA; V_{OSI} < 0.9 mB	MSOP-10	OUT A • -IN A • +IN A • V- • ENBL A • ENBL B • +IN B • -IN B • OUT B • V+
BHL	OPA2364AI	TI	dOA	R-R; V_{DD} = 1.85.5 B; f_{BD} = 7 MFu; I_S = 1.4 mA; V_{OSI} < 0.9 mB	MSOP-8	OUT A • -IN A • +IN A • V- • +IN B • -IN B • OUT B • V+
BJA	AD8626ARM	AD	dOA	$f_{BD} = 5 \text{ MFu}; P_D = 50 \text{ mBT}; V_{DD} = 526/±2.5±13 B$	MSOP-8	OUT A • -IN A • +IN A • V- • +IN B • -IN B • OUT B • V+
C1Y	AD7810YRM	AD	ADC	10-разр.; послед. интерфейс; V _{DD} = 2.75.5 B	MSOP-8	CONVST • VIN+ • VIN- • GND • VREF • DOUT • SCLK • VDD
C2T	AD7466BRMZ	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} = 1.63.6 B	MSOP-8	CS • SDATA • SCLK • n.c. • n.c. • VIN • GND • VDD
C2Y	AD7823YRM	AD	ADC	8-pasp.; I ² C; V ₀₀ = 2.75.5 B	MSOP-8	CONVST • VIN+ • VIN- • GND • VREF • DOUT • SCLK • VDD
СЗА	AD7818ARM	AD	ADC	10-pasp.; SPI/QSPI/Microwire; V ₀₀ = 2.75.5 B	MSOP-8	CONVST • OTI • GND • VIN • VDD • DIN/OUT • SCLK • RD/WR
C3B	AD7495ARMZ	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.75.25B	MSOP-8	REFOUT • VIN • GND • SCLK • SDATA • VDRIVE • CS • VDD
C3C	AD7475BRMZ	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.75.25 B	MSOP-8	REF IN • VIN • GND • SCLK • SDATA • VDRIVE • CS • VDD
C43	OPA2343EA	TI	dOA	R-R; V_{DD} = 2.55.5 B; f_{BD} = 5.5 MFu; I_S = 2.7 mA; V_{DS} < ± 8 mB	MSOP-8	OUT A • -IN A • +IN A • V- • +IN B • -IN B • OUT B • V+
C4A	AD7816ARM	AD	dts	10-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.75.5 B	MSOP-8	CONVST • OTI • GND • REFIN • VDD • DIN/OUT • SCLK • RD/WR
C50	OPA350EA	TI	CA	R-R; V _{DO} =2.75.5 B; f _{BD} =38 MFu; I _S =8.5 MA; V _{DS} <±1 MB	MSOP-8	n.c. • -IN • +IN • V- • n.c. • OUT • V+ • n.c.
C5A	AD7887ARM	AD	ADC	2x12-pasp; SPI/QSPI/Microwire; Vpp=2.75.25B	MSOP-8	CS • VDD • GND • AIN 1/VREF • AIN 0 • DIN • DOUT • SCLK
C6A	AD7416ARM	AD	dts	10-pasp.; I°C; V ₀₀ =2.75.5 B	MSOP-8	SDA • SCL • OTI • GND • A2 • A1 • A0 • VDD
C7A	AD7418ARM	AD	ADC	10-разр.; I ² C; V ₀₀ =2.75.5 В	MSOP-8	SDA • SCL • OTI • GND • AIN • REFIN • VDD • CONVST
C9A	AD7475ARM	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} =2.75.25B	MSOP-8	REF IN ◆VIN ◆ GND ◆ SCLK ◆ SDATA ◆ VDRIVE ◆ CS ◆ VDD
C9B	AD7475BRM	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.75.25B	MSOP-8	REF IN •VIN • GND • SCLK • SDATA • VDRIVE • CS • VDD
CAA	AD7814ARM	AD	dts	10-pasp.; SPI/QSPI/Microwire; V _{DD} =2.75.5 B	MSOP-8	n.c. • DOUT • CS • SCLK • VDD • DIN • GND • n.c.
CCA	AD7495ARM	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.75.25B	MSOP-8	REFOUT • VIN • GND • SCLK • SDATA • VDRIVE • CS • VDD
CCB	AD7495BRM	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.75.25B	MSOP-8	REF OUT • VIN • GND • SCLK • SDATA • VDRIVE • CS • VDD
CEW	AD7476AYRM	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.355.25B	MSOP-8	VDD • SDATA • CS • n.c. • n.c. • SCLK • GND • VIN
CEY	AD7476ABRM	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.355.25B	MSOP-8	VDD • SDATA • CS • n.c. • n.c. • SCLK • GND • VIN
CFZ	AD7477AARM	AD	ADC	10-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.355.25B	MSOP-8	VDD • SDATA • CS • n.c. • n.c. • SCLK • GND • VIN
CHA	AD7414ARM	AD	dts	10-разр.; SMBus/I ² C; V ₀₀ =2.75.5 В	MSOP-8	n.c. • SDA • ALERT • SCL • VDD • GND • AS • NC
CHB	AD7414ARM	AD	dts	10-разр.; SMBus/I ² C; V ₀₀ =2.75.5 В	MSOP-8	n.c. • SDA • ALERT • SCL • VDD • GND • AS • NC
CJZ	AD7478AARM	AD	ADC	8-pasp.; SPI/QSPI/Microwire; V _{DD} = 2.355.25B	MSOP-8	VDD • SDATA • CS • n.c. • n.c. • SCLK • GND • VIN
CKA	AD7314ARM	AD	dts	10-разр.; SPI; V ₀₀ = 2.655.5 В	MSOP-8	n.c. • CE • SCLK • GND • SDO • SDI • ID • VDD
CLB	AD7466BRM	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} = 1.63.6 B	MSOP-8	CS • SDATA • SCLK • n.c. • n.c. • VIN • GND • VDD
CMB	AD7467BRM	AD	ADC	10-pasp.; SPI/QSPI/Microwire; Vpp = 1.63.6 B	MSOP-8	CS • SDATA • SCLK • n.c. • n.c. • VIN • GND • VDD





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
CNA	AD7466ARM	AD	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} =1.63.6B	MSOP-8	CS • SDATA • SCLK • n.c. • n.c. • VIN • GND • VDD
CNB	AD7468BRM	AD	ADC	8-pasp.; SPI/QSPI/Microwire; V _{DD} = 1.63.6 B	MSOP-8	CS • SDATA • SCLK • n.c. • n.c. • VIN • GND • VDD
CNU	AD7468BRMZ	AD	ADC	8-pasp.; SPI/QSPI/Microwire; V _{DD} = 1.63.6 B	MSOP-8	CS • SDATA • SCLK • n.c. • n.c. • VIN • GND • VDD
CPA	AD7450ARM	AD	ADC	12-pasp.; SPI/Microwire; V ₀₀ =35.5B	MSOP-8	VREF • VIN+ • VIN- • GND • CS • SDATA • SCLK • VDD
CPB	AD7450BRM	AD	ADC	12-pasp.; SPI/Microwire; V ₀₀ =35.5B	MSOP-8	VREF • VIN+ • VIN- • GND • CS • SDATA • SCLK • VDD
CQA	AD7680ARM	AD	ADC	16-pasp.; SPI/QSPI/Microwire; V _{DD} =2.55.5B	MSOP-8	VDD • GND • GND • VIN • SCLK • n.c. • SDATA • CS
CQB	AD7680BRM	AD	ADC	16-pasp.; SPI/QSPI/Microwire; V ₀₀ =2.55.5B	MSOP-8	VDD • GND • GND • VIN • SCLK • n.c. • SDATA • CS
CUB	AD7920BRM	AD	ADC	12-pasp.; SPI/QSPI/Microwire; Vpp=2.355.25 B	MSOP-8	VDD • SDATA • CS • n.c. • n.c. • SCLK • GND • VIN
CVA	AD7910ARM	AD	ADC	10-pasp.; SPI/QSPI/Microwire; Vpp=2.355.25 B	MSOP-8	VDD • SDATA • CS • n.c. • n.c. • SCLK • GND • VIN
D13E	DAC7513E	TI	DAC	12-pasp.; SPI/QSPI/Microwire; Vpp=2.75.5B	MSOP-8	VDD • VREF • VFB • VOUT • SYNC • SCLK • DIN • GND
D13N	DAC7513N	TI	DAC	12-pasp.; SPI/QSPI/Microwire; Vpp=2.75.5B	SOT23-8	VOUT • VFB • VREF • VDD • GND • DIN • SCLK • SYNC
D1B	AD7303BRM	AD	DAC	2x8-pasp.; SPI/Microwire; V ₀₀ = 2.75.5 B	MSOP-8	VOUTA • VDD • GND • REF • SCLK • DIN • SYNC • VOUTB
D1P	AD5425YRM	AD	DAC	8-pasp.; SPI/Microwire; V ₀₀ = 2.55.5B	MSOP-10	IOUT1 • IOUT2 • GND • SCLK • SDIN • SYNC • LDAC • VDD • VREF • RFB
D1Q	AD5426YRM	AD	DAC	8-pasp.; SPI/Microwire; V _{DD} = 35.5B	MSOP-10	IOUT1 • IOUT2 • GND • SCLK • SDIN • SYNC • SDO • VDD • VREF • RFB
D1R	AD5432YRM	AD	DAC	10-разр.; SPI/Microwire; V _{DO} =35.5В	MSOP-10	IOUT1 • IOUT2 • GND • SCLK • SDIN • SYNC • SDO • VDD • VREF • RFB
D1S	AD5443YRM	AD	DAC	12-pasp.; SPI/Microwire; V ₀₀ =35.5B	MSOP-10	IOUT1 • IOUT2 • GND • SCLK • SDIN • SYNC • SDO • VDD • VREF • RFB
D22	OPA2822E	TI	dOA	V _{DD} =512 B; f _{BD} =100 MFu; I _S =10.4 mA; V _{DS} <±1.6 mB	SOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
D2B	AD5300BRM	AD	DAC	8-pasp.; SPI/Microwire; V _{DD} = 2.75.5B	MSOP-8	VDD ◆ n.c. ◆ n.c. ◆ VOUT ◆ SYNC ◆ SCLK ◆ DIN ◆ GND
DGB	AD5310BRM	AD	DAC	10-разр.; SPI/Microwire; V _{DD} =2.75.5 В	MSOP-8	VDD • n.c. • n.c. • VOUT • SYNC • SCLK • DIN • GND
D4B	AD5320BRM	AD	DAC	12-pasp.; SPI/Microwire; V ₀₀ =2.75.5 B	MSOP-8	VDD ◆ n.c. ◆ n.c. ◆ VOUT ◆ SYNC ◆ SCLK ◆ DIN ◆ GND
D 50	OPA2350EA	TI	dOA	R-R; V _{DD} = 2.75.5B; f _{BD} = 38 MFu; I _S = 8.5 mA; V _{DS} < ±1 mB	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
D55	OPA2355DGSA	TI	dOA	R-R; V _{DD} =2.75.5B; f _{BD} =200 MΓц; I _S =14 MA; V _{OSI} <±15 MB	MSOP-10	OUT A • -IN A • +IN A • V - • ENBL A • ENBL B • +IN B • -IN B • CUT B • V+
D5A	AD5302ARM	AD	DAC	2x8-pasp.; SPI/Microwire; V _{DD} = 2.55.5 B	MSOP-10	LDAC • VDD • VREFB • VREFA • VOUTA • VOUTB • SYNC • SCLK • DIN • GND
D5B	AD5302BRM	AD	DAC	2x8-pasp.; SPI/Microwire; V ₀₀ = 2.55.5 B	MSOP-10	LDAC • VDD • VREFB • VREFA • VOUTA • VOUTB • SYNC • SCLK • DIN • GND
D6A	AD5312ARM	AD	DAC	2x10-pasp.; SPI/Microwire; V ₀₀ = 2.55.5 B	MSOP-10	LDAC • VDD • VREFB • VREFA • VOUTA • VOUTB • SYNC • SCLK • DIN • GND
D6B	AD5312BRM	AD	DAC	2x10-pasp.; SPI/Microwire; V ₀₀ = 2.55.5B	MSOP-10	LDAC • VDD • VREFB • VREFA • VOUTA • VOUTB • SYNC • SCLK • DIN • GND
D6C	AD5322BRMZ	AD	DAC	2x12-pasp.; SPI/Microwire; V ₀₀ = 2.55.5 B	MSOP-10	LDAC • VDD • VREFB • VREFA • VOUTA • VOUTB • SYNC • SCLK • DIN • GND
D6T	AD5322ARMZ	AD	DAC	2x12-pasp.; SPI/Microwire; V ₀₀ = 2.55.5 B	MSOP-10	LDAC • VDD • VREFB • VREFA • VOUTA • VOUTB • SYNC • SCLK • DIN • GND
D6U	AD5443YRMZ	AD	DAC	12-pasp.; SPI/Microwire; V _{DD} =35.5B	MSOP-10	IOUT1 • IOUT2 • GND • SCLK • SDIN • SYNC • SDO • VDD • VREF • RFB





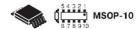
Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
D6V	AD5432YRMZ	AD	DAC	10-pasp.; SPI/Microwire; V _{DD} =35.5 B	MSOP-10	IOUT1 • IOUT2 • GND • SCLK • SDIN • SYNC • SDO • VDD • VREF • RFB
D6W	AD5426YRMZ	AD	DAC	8-разр.; SPI/Microwire; V ₀₀ =35.5 В	MSOP-10	IOUT1 • IOUT2 • GND • SCLK • SDIN • SYNC • SDO • VDD • VREF • RFB
D7A	AD5322ARM	AD	DAC	2x 12-pasp.; SPI/Microwire; V ₀₀ = 2.55.5 B	MSOP-10	LDAC • VDD • VREFB • VREFA • VOUTA • VOUTB • SYNC • SCLK • DIN • GND
D7B	AD5322BRM	AD	DAC	2x 12-pasp.; SPI/Microwire; V ₀₀ = 2.55.5 B	MSOP-10	LDAC • VDD • VREFB • VREFA • VOUTA • VOUTB • SYNC • SCLK • DIN • GND
D8B	AD5301BRM	AD	DAC	8-pasp.; I ² C; V ₀₀ =2.75.5 B	MSOP-8	VDD • A0 • A1 • VOUT • PD • SCL • SDA • GND
V80	AD5302ARMZ	AD	DAC	2x8-pasp.; SPI/Microwire; V _{DO} = 2.55.5 B	MSOP-10	LDAC • VDD • VREFB • VREFA • VOUTA • VOUTB • SYNC • SCLK • DIN • GND
D8W	AD5302BRMZ	AD	DAC	2x8-pasp.; SPI/Microwire; V ₀₀ = 2.55.5 B	MSOP-10	LDAC • VDD • VREFB • VREFA • VOUTA • VOUTB • SYNC • SCLK • DIN • GND
D8X	AD5312ARMZ	AD	DAC	2x 10-pasp.; SPI/Microwire; V ₀₀ =2.55.5 B	MSOP-10	LDAC • VDD • VREFB • VREFA • VOUTA • VOUTB • SYNC • SCLK • DIN • GND
D8Y	AD5312BRMZ	AD	DAC	2x 10-pasp.; SPI/Microwire; V ₀₀ =2.55.5 B	MSOP-10	LDAC • VDD • VREFB • VREFA • VOUTA • VOUTB • SYNC • SCLK • DIN • GND
D9B	AD5311BRM	AD	DAC	10-pasp.; I ² C; V _{DO} = 2.75.5B	MSOP-8	VDD • A0 • A1 • VOUT • PD • SCL • SDA • GND
D9N	AD5320BRMZ	AD	DAC	12-pasp.; SPI/Microwire; V ₀₀ =2.75.5 B	MSOP-8	VDD ● n.c. ● n.c. ● VOUT ● SYNC ● SCLK ● DIN ● GND
DAB	AD5321BRM	AD	DAC	12-pasp.; I ² C; V ₀₀ = 2.75.5B	MSOP-8	VDD • A0 • A1 • VOUT • PD • SCL • SDA • GND
OBA	AD5304ARM	AD	DAC	4x8-pasp.; SPI/Microwire; V ₀₀ = 2.55.5 B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
OBB	AD5304BRM	AD	DAC	4x 8-pasp.; SPI/Microwire; V _{DO} = 2.55.5 B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
DCA	AD5314ARM	AD	DAC	4x 10-pasp.; SPI/Microwire; V _{DD} = 2.55.5 B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
DCB	AD5314BRM	AD	DAC	4x 10-pasp.; SPI/Microwire; V _{DD} =2.55.5 B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
DDA	AD5324ARM	AD	DAC	4x12-pasp.; SPI/Microwire; V _{DD} =2.55.5 B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
DDB	AD5324BRM	AD	DAC	4x 12-pasp.; SPI/Microwire; V _{DD} = 2.55.5 B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
DEA	AD5305ARM	AD	DAC	4x 8-pasp.; I ² C; V _{DD} = 2.55.5 B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • SDA • SCL • A0
DEB	AD5305BRM	AD	DAC	4x 8-pasp.; I ² C; V _{DD} = 2.55.5 B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • SDA • SCL • A0
DFA	AD5315ARM	AD	DAC	4x 10-pasp.; I ² C; V ₀₀ = 2.55.5 B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • SDA • SCL • A0
DFB	AD5315BRM	AD	DAC	4x 10-pasp.; I ² C; V _{DO} = 2.55.5 B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • SDA • SCL • A0
DGA	AD5325ARM	AD	DAC	4x 12-pasp.; I°C; V _{DD} = 2.55.5 B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • SDA • SCL • A0
DGB	AD5325BRM	AD	DAC	4x 12-pasp.; I°C; V _{DO} = 2.55.5 B	MSOP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • SDA • SCL • A0
λJB	AD9833BRM	AD	gen	f_{OUT} < 12.5 MFu; P_D = 30 MBT; V_{OO} = 2.35.5 B	MSOP-10	COMP • VDD • CAP/2:5V • DGND • MCLK • SDATA • SCLK • FSYNC • AGND • VOUT
DLA	AD5200BRM-10	AD	Dpot	256 позиций; 10 кОм; SPI	MSOP-10	B • VSS • GND • CS • SDI • CLK • SHDN • VDD • W • A
DLB	AD5200BRM-50	AD	Dpot	256 позиций; 50 кОм; SPI	MSOP-10	B • VSS • GND • CS • SDI • CLK • SHDN • VDD • W • A
DMA	AD5201BRM-10	AD	Dpot	33 позиции; 10 кОм; SPI	MSOP-10	B • VSS • GND • CS • SDI • CLK • SHDN • VDD • W • A
DMB	AD5201BRM-50	AD	Dpot	33 позиции; 50 кОм; SPI	MSOP-10	B • VSS • GND • CS • SDI • CLK • SHDN • VDD • W • A



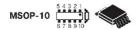


Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
DSB	AD5399RM	AD	DAC	2x12-pasp.; SPI/Microwire; V ₀₀ = 4.55.5B	MSOP-10	CLK • SDI • DGND • VOUTB • VOUTA • VBZ • AGND • VDD • VTP • CS
DUC	AD5553CRM	AD	DAC	14-разр.; SPI; V _{DD} =4.55.5 В	MSOP-8	CLK • SDI • RFB • VREF • IOUT • GND • VDD • CS
DXB	AD5543BRM	AD	DAC	16-разр.; SPI; V _{DD} =4.55.5 В	MSOP-8	CLK • SDI • RFB • VREF • IOUT • GND • VDD • CS
DYA	AD5273BRJ1	AD	Dpot	64 позиции; 1 кОм; ОТР; I ² С	SOT23-8	W • VDD • GND • SCL • SDA • ADO • B • A
DYB	AD5273BRJ10	AD	Dpot	64 позиции; 10 кОм; ОТР; I ² C	SOT23-8	W • VDD • GND • SCL • SDA • ADO • B • A
DYC	AD5273BRJ50	AD	Doot	64 позиции; 50 кОм; ОТР; I ² C	SOT23-8	W.VDD.GND.SCL.SDA.ADO.B.A
DYD	AD5273BRJ100	AD	Doot	64 позиции: 100 кОм: ОТР: I ² C	SOT23-8	W • VDD • GND • SCL • SDA • ADO • B • A
E37	OPA2137EA	TI	dOA	V _{DD} =4.536/±2.25±18 В; I _S =600 мкА; V _{DS} < ±7 мВ	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
E43	OPA2743EA	TI	dOA	R-R; V_{DD} = 3.512/±1.75±6B; f_{BD} = 7MF μ ; I_S = 1.7 mA; V_{DS} < ±7 mB	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
E53	OPA2353EA	TI	dOA	R-R; V_{DD} = 2.75.5B; f_{BD} = 44 MFu; I_S = 9 mA; V_{DSI} < ±10 mB	MSOP-8	OUT A • -IN A • +IN A • V - • +IN B • -IN B • OUT B • V+
G1A	AD8611ARM	AD	стр	f _{IN} = 100 МГц; Р _D = 14 мВт; V _{DD} = 35 В	MSOP-8	V+ • +IN • -IN • V- • LATCH • GND • OUT • OUT
G37	OPA337EA	TI	OA	$\begin{array}{l} \text{R-R; V}_{DD}\!=\!2.55.5\text{B; f}_{BO}\!=\!3\text{MFu; I}_S\!=\!1.2\text{mA;} \\ \text{V}_{DS}\!<\!\pm\!3.5\text{mB} \end{array}$	MSOP-8	n.c. • -IN • +IN • V- • n.c. • OUT • V+ • n.c.
H1B	AD8066ARM	AD	dOA	f _{BD} = 145 МГц; P _D = 150 мВт; V _{DD} = 524 В	MSOP-8	VOUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • VOUT2 • +VS
H2B	AD8008ARM	AD	dOA	$f_{BD} = 650 \text{MFu}; P_D = 120 \text{mBr}; V_{DO} = 512 \text{B}$	MSOP-8	VOUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • VOUT2 • +VS
Н4А	AD8052ARM	AD	AOb	$f_{BD} = 110 \text{ MFu}; P_D = 60 \text{ mBT}; V_{DD} = 312 \text{ B}$	MSOP-8	OUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • OUT2 • +VS
H5A	AD8056ARM	AD	dOA	$f_{BD} = 300 \text{ MFu}; P_D = 40 \text{ mBT}; V_{DO} = \pm 4\pm 6 \text{ B}$	MSOP-8	OUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • OUT2 • +VS
H5B	AD8028ARM	AD	dOA	$f_{BD} = 185 \text{ MFu}; P_D = 100 \text{ mBr}; V_{DD} = 2.712 \text{B}$	MSOP-10	VOUTA ● -IN A ● -IN A ● -VS ● DIS/SEL A ● DIS/SEL B ● +IN B ● -IN B ● VOUTB ● +VS
H5B#	AD8028ARMZ	AD	dOA	$f_{BD} = 185 \text{ MFu}; P_D = 100 \text{ mBr}; V_{DO} = 2.712 \text{ B}$	MSOP-10	VOUTA ● -IN A ● -IN A ● -VS ● DIS/SEL A ● DIS/SEL B ● +IN B ● -IN B ● VOUTB ● +VS
H6A	AD8012ARM	AD	dOA	$f_{BD} = 350 \text{ MFu}; P_D = 12 \text{ mBT}; V_{DD} = \pm 1.5\pm 6 \text{ B}$	MSOP-8	OUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • OUT2 • +VS
H7B	AD8030ARJ	AD	dOA	$f_{BD} = 120 \text{ MFu}; P_D = 18 \text{ mBr}; V_{DD} = 2.712 \text{ B}$	SOT23-8	VOUT 1 • -IN 1 • +IN 1 • -VS • +IN 2 • -IN 2 • +VOUT 2 • +VS
H7C	AD8066ARMZ	AD	dOA	$f_{BD} = 145 \text{MFu}; P_D = 150 \text{mBT}; V_{DO} = 524 \text{B}$	MSOP-8	VOUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • VOUT2 • +VS
ABH	AD8058ARM	AD	AOb	$f_{BD} = 325 \text{MFu}; P_D = 70 \text{mBT}; V_{DO} = 312 \text{B}$	MSOP-8	OUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • OUT2 • +VS
H9A	AD8032ARM	AD	dOA	f _{BD} = 80 МГц; P _D = 16 мВт; V _{DD} = 2.712 В	MSOP-8	OUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • OUT2 • +VS
HCA	AD8062ARM	AD	dOA	$f_{BD} = 320 M\Gamma ц; P_D = 75 MBT; V_{DD} = 2.78 B$	MSOP-8	VOUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • VOUT2 • +VS
HDA	AD8022ARM	AD	dOA	$f_{BD} = 130 \text{ MFu}; P_D = 55 \text{ mBr}; V_{DO} = \pm 4.5 \pm 13 \text{ B}$	MSOP-8	OUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • OUT2 • +VS
HDB	AD8022ARMZ	AD	dOA	$f_{BO} = 130 M\Gamma_{II}; P_D = 55 MBT; V_{DO} = \pm 4.5 \pm 13 B$	MSOP-8	OUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • OUT2 • +VS
HFA	AD8002ARM	AD	dOA	$f_{BD} = 600 \text{ MFu}; P_D = 55 \text{ MBt}; V_{DD} = \pm 3 \pm 6 \text{ B}$	MSOP-8	OUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • OUT2 • +VS
HKJ	AD8009ARM	AD	OA	$f_{BD} = 1\Gamma\Gamma u_i P_D = 100 \text{ MBT}; V_{DD} = \pm 4\pm 6 \text{ B}$	SOT23-8	n.c. • -IN • +IN • -VS • n.c. • OUT • +VS • n.c.
HLA	AD8072JR	AD	dOA	$f_{BD} = 100 \text{ MFu}; P_D = 30 \text{ MBt}; V_{DD} = \pm 2.5\pm 6 \text{ B}$	MSOP-8	OUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • OUT2 • +VS
HMA	AD8132ARM	AD	OA	f_{BD} = 350 МГц, P_D = 70 мВт, V_{DD} = ±1.35±5.5	MSOP-8	-IN • VOCM • V+ • +OUT • -OUT • V- • n.c. • +IN
HMA#	AD8132ARMZ	AD	OA	$f_{BD} = 350 \text{MFu}; P_D = 70 \text{mBt}; \\ V_{DD} = \pm 1.35 \pm 5.5 \text{B}$	MSOP-8	-IN • VOCM • V+ • +OUT • -OUT • V - • n.c. • +IN





Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
HNA	AD8021ARM	AD	CA	f _{BD} = 490 МГц; P _D = 100 мВт; V _{DD} = ±2.25±12 В	MSOP-8	LOG REF • -IN • +IN • -VS • CCOMP • VOUT • +VS • DIS
HNA	AD8021ARMZ	AD	CA	f _{BD} = 490 МГц; P _D = 100 мВт; V _{DD} = ±2.25±12 В	MSOP-8	LOG REF • -IN • +IN • -VS • CCOMP • VOUT • +VS • DIS
HWA	AD8092ARM	AD	dOA	f _{BD} = 110 МГц; P _D = 60 мВт; V _{DD} = 312 В	MSOP-8	OUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • OUT • +VS
HWA#	AD8092ARMZ	AD	dOA	$f_{BD} = 110 \text{ MFu}; P_D = 60 \text{ mBr}; V_{DO} = 312 \text{ B}$	MSOP-8	OUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • OUT • +VS
HYA	AD8039ART	AD	dOA	f _{BD} =350 МГц; P _D =18 мВт; V _{DD} =312 В	SOT23-8	VOUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • VOUT2 • +VS
HZA	AD8034ART	AD	dOA	$f_{BO} = 80 \text{ MFu}; P_D = 65 \text{ MBt}; V_{DO} = 524 \text{ B}$	SOT23-8	VOUT1 • -IN1 • +IN1 • -VS • +IN2 • -IN2 • VOUT2 • +VS
J0A	AD623ARM	AD	IA	V _{DD} =312 B; Gain = 11000; V _{DSI} < 500 мкВ	MSOP-8	-RG • -IN • +IN • -VS • REF • CUTPUT • +VS • +RG
J1A	AD8313ARM	AD	LA	f _{BD} = 0.12.5ГГц; DD = 70 дБ; P _D = 60 мВт; V _{DD} = 2.75.5 В	MSOP-8	VPOS • INHI • INLO • VPOS • PWDN • COMM • VSET • VOUT
J2N	AD8350ARM15	AD	DA	f _{BD} =1.1ГГц; Gain=15,дБ; P _D =330 мВт; V _{DD} =411 В	MSOP-8	IN+ • ENBL • VCC • OUT+ • OUT- • GND • GND • IN-
J2P	AD8350ARM20	AD	DA	f _{BD} = 1.1 ГГц; Gain = 20 дБ; P _D = 330 мВт; V _{DD} = 411 В	MSOP-8	IN+ • ENBL • VCC • OUT+ • OUT- • GND • GND • IN-
J3A	AD8361ARM	AD	PD	f_{BO} < 2.5 ГГц; P_D = 12 мВт; V_{DO} = 2.75.5 В	MSOP-8	VPOS • IREF • RFIN • PWDN • COMM • FLTR • VRMS • SREF
J5A	AD8314ARM	AD	LA	f _{BD} =0.12.7ГГц; P _D =30 мВт; V _{DD} =2.75.5 В	MSOP-8	RFIN • ENBL • VSET • FLTR • COMM • V UP • V DN • VPOS
J6A	AD8310ARM	AD	LA	f_{BD} < 440 MFu; DD = 95 μ B; P_{D} = 50 μ BT; V_{DD} = 2.75.5 B	MSOP-8	INLO • COMM • OFLT • VOUT • VPOS • BFIN • ENBL • INHI
J7A	AD8315ARM	AD	LA	f _{BD} =0.12.5ГГц; P _D =60 мВт; V _{DD} =2.75.5 В	MSOP-8	RFIN • ENBL • VSET • FLTR • COMM • n.c. • VAPC • VPOS
J8A	AD8316ARM	AD	LA	f _{BO} =0.12.5ГГц; Р _D =60 мВт; V _{DD} =2.75.5 В	MSOP-10	RFIN • ENBL • VSET • FLTR • BSEL • FLT2 • OUT2 • COMM • OUT1 • VPOS
LOC	ADR420ARMZ	AD	vref	XFET®; V _{IN} =418 B; I _{OUT} = 10 mA; V _{OUT} = 2.048 B	MSOP-8	TP • VIN • n.c. • GND • TRIM • VOUT • n.c. • TP
L7	NLAS324US	ON	asw	2x SPST; R _{ON} < 55 OM; V _{DO} = 2.76.0 B	US-8	NC1 • COM1 • IN2 • GND • NC2 • COM2 • IN1 • VCC
L7	NLAS325US	ON	asw	2x SPST; R _{DN} < 105 OM; V _{DO} = 2.76.0B	US-8	NO1 • COM1 • IN2 • GND • NC2 • COM2 • IN1 • VCC
LFA	ADP3335ARM-1.8	AD	reg	LDO; V _{IN} = 2.612B; I _{DUT} = 500 mA; V _{DUT} = 1.8 B	MSOP-8	OUT • OUT • OUT • GND • NR • SD • IN • IN
LFC	ADP3335ARM-2.5	AD	reg	LDO; V _{IN} = 2.612B; I _{DUT} = 500 mA; V _{DUT} = 2.5 B	MSOP-8	OUT • OUT • OUT • GND • NR • SD • IN • IN
LFD	ADP3335ARM-2.85	AD	reg	LDO; V _{IN} = 2.612B; I _{DUT} = 500 mA; V _{DUT} = 2.85 B	MSOP-8	OUT • OUT • OUT • GND • NR • SD • IN • IN
LFE	ADP3335ARM-3.3	AD	reg	LDO; V _{IN} = 2.612B; I _{DUT} = 500 MA; V _{OUT} = 3.3B	MSOP-8	OUT • OUT • OUT • GND • NR • SD • IN • IN
LFF	ADP3335ARM-5	AD	reg	LDO; V _{IN} = 2.612B; I _{DLII} = 500 MA; V _{DLII} = 5B	MSOP-8	OUT • OUT • OUT • GND • NR • SD • IN • IN
LHA	ADP3336ARM	AD	reg	LDO; V _{IN} = 2.612B; I _{DUT} = 500 мA; V _{DUT} = 1.510B	MSOP-8	OUT • OUT • OUT • GND • FB • SD • IN • IN
LKA	ADP3333ARM-1.5	AD	reg	LDO; V _{IN} = 2.612B; I _{DUT} = 300 мA; V _{OUT} = 1.5 B	MSOP-8	OUT • IN • GND • n.c. • n.c. • n.c. • SD • n.c.
LKB	ADP3333ARM-1.8	AD	reg	LDO; V _{IN} = 2.612B; I _{DUT} = 300 MA; V _{OUT} = 1.8 B	MSOP-8	OUT • IN • GND • n.c. • n.c. • n.c. • SD • n.c.
LKC	ADP3333ARM-2.5	AD	reg	LDO; V _{IN} = 2.612B; I _{DUT} = 300 мA; V _{OUT} = 2.5 B	MSOP-8	OUT • IN • GND • n.c. • n.c. • n.c. • SD • n.c.
LKD	ADP3333ARM-2.77	AD	reg	LDO; V _{IN} = 2.612B; I _{DUT} = 300 мA; V _{OUT} = 2.77 B	MSOP-8	OUT • IN • GND • n.c. • n.c. • n.c. • SD • n.c.
LKE	ADP3333ARM-3	AD	reg		MSOP-8	OUT • IN • GND • n.c. • n.c. • n.c. • SD • n.c.
LKF	ADP3333ARM-3.15	AD	reg	LDO; V _{IN} = 2.612B; I _{DUT} = 300 мA; V _{OUT} = 3.15 B	MSOP-8	OUT • IN • GND • n.c. • n.c. • n.c. • SD • n.c.
LKG	ADP3333ARM-3.3	AD	req	LDD; V _{IN} = 2.6 12B; I _{OUT} = 300 mA; V _{OUT} = 3.3B	MSOP-8	OUT • IN • GND • n.c. • n.c. • n.c. • SD • n.c.





Код	Типономинал	6	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
LKH	ADP3333ARM-5	AD	reg	LDO; V _{IN} = 2.612B; I _{OUT} = 300 mA; V _{OUT} = 5 B	MSOP-8	OUT • IN • GND • n.c. • n.c. • n.c. • SD • n.c
LTQZ	LT1009CMS8	LT	vref	V _{DUT} = 2.5 B; ACC < 0.2 %; T _{AMB} = 070 °C	MSOP-8	n.c. • n.c. • n.c. • (-) • ADJ • (+) • n.c. • (+)
M01	ADM101EARM	AD	trans	RS-232; 460 кбит/с; V ₀₀ = 4.55.5 В	MSOP-10	GND • C1 - • V - • TIN • ROUT • RIN • TOUT • SD • C1 + • VCC
M2B	ADM1232ARM	AD	mrc	V _{TR} =4.62 B(5%)/4.37 B(10%); V _{DD} =4.55.5 B; I _{CC} < 0.5 mA	MSOP-8	PB RES • TD • TOL • GND • RES • RES • STR • VCC
POA.	ADP3088ARM	AD	reg	V_{IN} = 2.511 B; I_{DUT} = 750 mA; I_{DSC} = 1 MFu; V_{DUT} = 1.2510.5 B	MSOP-8	IN • IN • GND • COMP • FB • GND • DRV • SW
P1E	ADP3415LRM	AD	drv	R _{OUT} < 3 Om; V _{CC} = 5 B; I _{CC} < 2 mA	MSOP-10	IN • SD • DRVLSD • DLY • VCC • DRVL • GND • SW • DRVH • BST
R06	ADR421ARMZ	AD	vref	XFET®; V _{IN} = 4.518 B; I _{OUT} = 10 mA; V _{OUT} = 2.5 B	MSOP-8	TP • VIN • n.c. • GND • TRIM • VOUT • n.c. • TP
ROU	ADR423ARMZ	AD	vref	XFET@; V _{IN} = 518 B; I _{OUT} = 10 mA; V _{OUT} = 3 B	MSOP-8	TP • VIN • n.c. • GND • TRIM • VOUT • n.c. • TP
ROV	ADR425ARMZ	AD	vref	XFET®; V _{IN} = 718 B; I _{OUT} = 10 mA; V _{OUT} = 5 B	MSOP-8	TP • VIN • n.c. • GND • TRIM • VOUT • n.c. • TP
R4A	ADR420ARM	AD	vref	XFET®; V _{IN} =418 B; I _{OUT} = 10 mA; V _{DUT} = 2.048 B	MSOP-8	TP • VIN • n.c. • GND • TRIM • VOUT • n.c. • TP
R5A	ADR421ARM	AD	vref	XFET®; V _{IN} = 4.518 B; I _{OUT} = 10 mA; V _{OUT} = 2.5 B	MSOP-8	TP • VIN • n.c. • GND • TRIM • VOUT • n.c. • TP
R6A	ADR423ARM	AD	vref	XFET@; V _{IN} = 518 B; I _{OUT} = 10 mA; V _{OUT} = 3 B	MSOP-8	TP • VIN • n.c. • GND • TRIM • VOUT • n.c. • TP
R7A	ADR425ARM	AD	vref	XFET@; V _{IN} = 718 B; I _{OUT} = 10 mA; V _{OUT} = 5 B	MSOP-8	TP • VIN • n.c. • GND • TRIM • VOUT • n.c. • TP
RHA	ADR430ARM	AD	vref	XFET®; V _{IN} = 4.118 B; I _{CUT} = +30/-20 мA; V _{CUT} = 2.048 B	MSOP-8	TP • VIN • n.c. • GND • TRIM • VOUT • n.c. • TP
RJA	ADR431ARM	AD	vref	XFET®; V _{IN} = 4.518 B; I _{OUT} = +30/-20 мA; V _{OUT} = 2.5 B	MSOP-8	TP • VIN • n.c. • GND • TRIM • VOUT • n.c. •
RKA	ADR433ARM	AD	vref	XFET®; V _{IN} = 518 B; I _{OUT} = +30/-20 mA; V _{OUT} = 3 B	MSOP-8	TP • VIN • n.c. • GND • TRIM • VOUT • n.c. • TP
RLA	ADR434ARM	AD	vref	XFET®; V _{IN} = 6.118 B; I _{OUT} = +30/-20 mA; V _{OUT} = 4.096 B	MSOP-8	TP • VIN • n.c. • GND • TRIM • VOUT • n.c. • TP
RMA	ADR435ARM	AD	vref	XFET®; V _{IN} = 718 B; I _{OUT} = +30/-20 mA; V _{OUT} = 5 B	MSOP-8	TP • VIN • n.c. • GND • TRIM • VOUT • n.c. • TP
RNA	ADR439ARM	AD	vref	XFET®; V _{IN} = 6.518 B; I _{OUT} = +30/-20 мA; V _{DUT} = 4.5 B	MSOP-8	TP • VIN • n.c. • GND • TRIM • VOUT • n.c. •
S18	ADG602BRMZ	AD	asw	SPST; R _{ON} < 5.5OM; V _{DD} = 2.75.5/±2.7±5.5B	MSOP-8	D • n.c. • n.c. • VDD • VSS • IN • GND • S
S1B	ADG465BRM	AD	prot	V _{PROT} <±40B; V _{DD} =±15B	MSOP-8	n.c. • VDD • VS1 • n.c. • n.c. • VSS • VD1 • n.c.
S1G	ADG601BRMZ	AD	asw	SPST; R _{ON} < 5.5 OM; V _{DD} = 2.7 5.5/±2.7 ±5.5 B	MSOP-8	D•n.c.•n.c.•VDD•VSS•IN•GND•S
S21	ADG620BRMZ	AD	asw	SPDT; R _{DN} < 8.5 CM; V _{DD} = 2.75.5/±2.7±5.5 B	MSOP-8	D•S1•GND•VDD•n.c.•IN•VSS•S2
S21	ADG620BRTZ	AD	asw	SPDT; R _{ON} < 8.5 CM; V _{DD} = 2.75.5/±2.7±5.5 B	SOT23-8	D•S1•GND•VDD•n.c.•IN•VSS•S2
S29B	LM3485MM	NS	SPM	V _{IN} =4.535 B; V _{OUT} = 1.242V _{IN} B	MSOP-8	ISENSE • GND • n.c. • FB • ADJ • PWR GND • PGATE • VIN
S3B	ADG701BRM	AD	asw	SPST; R _{DN} < 40m; V _{DD} = 1.85.5 B	MSOP-8	D • n.c. • n.c. • VDD • n.c. • IN • GND • S
S4B	ADG702BRM	AD	asw	SPST; R _{DN} < 40 _M ; V _{DD} = 1.85.5 B	MSOP-8	D • n.c. • n.c. • VDD • n.c. • IN • GND • S
S5B	ADG719BRM	AD	asw	SPDT; R _{DN} < 70m; V _{DO} = 1.85.5 B	MSOP-8	D • S1 • GND • VDD • n.c. • IN • n.c. • S2
S6B	ADG721BRM	AD	asw	2xSPST; R _{DN} < 5Om; V _{DD} = 1.85.5 B	MSOP-8	S1 • D1 • IN2 • GND • S2 • D2 • IN1 • VDD
S7B	ADG722BRM	AD	asw	2xSPST; R _{DN} < 5Om; V _{DD} = 1.85.5 B	MSOP-8	S1 • D1 • IN2 • GND • S2 • D2 • IN1 • VDD
S8B	ADG723BRM	AD	asw	2xSPST; R _{DN} < 5OM; V _{DD} = 1.85.5 B	MSOP-8	S1 • D1 • IN2 • GND • S2 • D2 • IN1 • VDD
S9B	ADG704BRM	AD	amux	4 канала; R _{ON} < 4.5 Ом; V _{DO} = 1.85.5 В	MSOP-10	A0 • S1 • GND • S3 • EN • VDD • S4 • D • S2 • A1
SAB	ADG736BRM	AD	asw	2xSPDT; R _{DN} < 4.5OM; V _{DD} = 1.85.5 B	MSOP-10	IN1 • S1A • GND • S2A • IN2 • D2 • S2B • VDD • S1B • D1





MSOP-8 SOT23-8 US-8 (\$\frac{4321}{5678}\$ MSOP-8 TSOT23-8 US-8

Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6•7•8•9•10
SBB	ADG419BRM	AD	asw	SPDT; R _{DN} < 70 OM; V _{DD} = ± 15B; V _L = 5B	MSOP-8	D • S1 • GND • VDD • VL • IN • VSS • S2
SCC	ADG619BRMZ	AD	asw	SPDT; R _{DN} < 8.5 OM; V _{DD} = 2.75.5/±2.7±5.5B	MSOP-8	D•S1•GND•VDD•n.c.•IN•VSS•S2
SCC	ADG619BRTZ	AD	asw	SPDT; R _{DN} < 8.5 OM; V _{DD} = 2.75.5/±2.7±5.5 B	SOT23-8	D • S1 • GND • VDD • n.c. • IN • VSS • S2
SDA	ADG751ARM	AD	asw	SPST; R _{ON} < 40 OM; V _{DO} = 1.85.5 B	MSOP-8	n.c. • S • GND • IN • n.c. • n.c. • D • VDD
SDB	ADG751BRM	AD	asw	SPST; R _{ON} < 40 OM; V _{DD} = 1.85.5 B	MSOP-8	n.c. • S • GND • IN • n.c. • n.c. • D • VDD
SEB	ADG752BRM	AD	asw	SPDT; R _{DN} < 20 OM; V _{DD} = 1.85.5B	MSOP-8	n.c. • S2 • GND • IN • n.c. • S1 • VDD • D
SLB	ADG801BRM	AD	asw	SPST; R _{ON} < 0.4 OM; V _{DO} = 1.85.5 B	MSOP-8	D • n.c. • n.c. • VDD • n.c. • IN • GND • S
SMB	ADG802BRM	AD	asw	SPST; R _{ON} < 0.4 Om; V _{DO} = 1.85.5 B	MSOP-8	D • n.c. • n.c. • VDD • n.c. • IN • GND • S
SNB	ADG819BRM	AD	asw	SPDT; R _{DN} < 0.8 Om; V _{DD} = 1.85.5 B	MSOP-8	D • S1 • GND • VDD • n.c. • IN • n.c. • S2
SPB	ADG820BRM	AD	asw	SPDT; R _{DN} < 0.8 O _M ; V _{DD} = 1.85.5 B	MSOP-8	D • S1 • GND • VDD • n.c. • IN • n.c. • S2
SQB	ADG821BRM	AD	asw	2x SPST; R _{ON} < 0.8 OM; V _{DD} = 1.85.5 B	MSOP-8	S1 • D1 • IN2 • GND • S2 • D2 • IN1 • VDD
SRB	ADG822BRM	AD	asw	2x SPST; R _{DN} < 0.8 OM; V _{DD} = 1.85.5 B	MSOP-8	S1 • D1 • IN2 • GND • S2 • D2 • IN1 • VDD
SSB	ADG823BRM	AD	asw	2x SPST; R _{DN} < 0.8 OM; V _{DD} = 1.85.5 B	MSOP-8	S1 • D1 • IN2 • GND • S2 • D2 • IN1 • VDD
STB	ADG601BRM	AD	asw	SPST; R _{ON} < 5.5 OM; V _{DD} = 2.75.5/±2.7±5.5B	MSOP-8	D • n.c. • n.c. • VDD • VSS • IN • GND • S
SUB	ADG602BRM	AD	asw	SPST; R _{DN} < 5.5 OM; V _{DD} = 2.75.5/±2.7±5.5B	MSOP-8	D • n.c. • n.c. • VDD • VSS • IN • GND • S
SVB	ADG619BRM	AD	asw	SPDT; R _{DN} < 8.5 OM; V _{DD} = 2.75.5/±2.7±5.5B	MSOP-8	D • S1 • GND • VDD • n.c. • IN • VSS • S2
SVB	ADG619BRT	AD	asw	SPDT; R _{DN} < 8.5 OM; V _{DD} = 2.75.5/±2.7±5.5B	SOT23-8	D • S1 • GND • VDD • n.c. • IN • VSS • S2
SWB	ADG620BRM	AD	asw	SPDT; R _{DN} < 8.5 OM; V _{DD} = 2.75.5/±2.7±5.5B	MSOP-8	D • S1 • GND • VDD • n.c. • IN • VSS • S2
SWB	ADG620BRT	AD	asw	SPDT; R _{DN} < 8.5 OM; V _{DD} = 2.75.5/±2.7±5.5B	SOT23-8	D•S1•GND•VDD•n.c.•IN•VSS•S2
SXB	ADG621BRM	AD	asw	2x SPST; R _{DN} < 70м; V _{DD} = 2.75.5/±2.7±5.5В	MSOP-10	S1 • D1 • IN2 • GND • VSS • n.c. • S2 • D2 • IN1 • VDD
SYB	ADG622BRM	AD	asw	2x SPST; R _{ON} < 70м; V _{OD} = 2.75.5/±2.7±5.5В	MSOP-10	S1 • D1 • IN2 • GND • VSS • n.c. • S2 • D2 • IN1 • VDD
SZB	ADG623BRM	AD	asw	2x SPST; R _{DN} < 70m; V _{DD} = 2.75.5/±2.7±5.5B	MSOP-10	S1 • D1 • IN2 • GND • VSS • n.c. • S2 • D2 • IN1 • VDD
T13	ADM1032ARMZ-1	AD	dts	2канала; 108°С; SMBus; V ₀₀ =35.5В	MSOP-8	VDD • D+ • D- • THERM • GND • ALERT • SDATA • SCLK
T1A	ADM1032ARM-1	AD	dts	2канала; 108°С; SMBus; V ₀₀ =35.5В	MSOP-8	VDD • D+ • D- • THERM • GND • ALERT • SDATA • SCLK
T1C	ADM1032ARMZ-2	AD	dts	2канала; 85°C; SMBus; V ₀₀ =35.5B	MSOP-8	VDD • D+ • D− • THERM • GND • ALERT • SDATA • SCLK
T1H	ADT7301ARMZ	AD	dts	13-pasp.; SPI/QSPI/Microwire; V ₀₀ =2.75.25 B	MSOP-8	n.c. • DOUT • CS • SCLK • VDD • DIN • GND • n.c.
T1J	ADM1032ARMZ	AD	dts	2канала; 85°С; SMBus; V ₀₀ =35.5B	MSOP-8	VDD • D+ • D− • THERM • GND • ALERT • SDATA • SCLK
T2A	ADM1032ARM	AD	dts	2канала; 85°С; SMBus; V _{DD} =35.5B	MSOP-8	VDD • D+ • D− • THERM • GND • ALERT • SDATA • SCLK
TOH	AD7414ARMZ	AD	dts	10-разр.; SMBus/I ² C; V ₀₀ =2.75.5 В	MSOP-8	n.c. • SDA • ALERT • SCL • VDD • GND • AS • NC
TOL	AD7414ARMZ	AD	dts	10-разр.; SMBus/I ² C; V ₀₀ =2.75.5 В	MSOP-8	n.c. • SDA • ALERT • SCL • VDD • GND • AS • NC
/0K	AD7740KRM	AD	VFC	V _{DD} =33.6 B/4.755.25 B; синхронный	MSOP-8	CLKOUT • CLKIN • GND • REFIN/OUT • VIN • VDD • FOUT • BUF
/0Y	AD7740YRM	AD	VFC	V ₀₀ = 33.6 B/4.755.25 B; синхронный	MSOP-8	CLKOUT • CLKIN • GND • REFIN/OUT • VIN • VDD • FOUT • BUF
/0Y	AD7740YRT	AD	VFC	V ₀₀ =33.6 B/4.755.25 В; синхронный	SOT23-8	BUF • FOUT • VDD • VIN • REFIN/OUT • GND • CLKIN • CLKOUT
N1B	ADG3233BRJ	AD	dsw	t _{PO} < 10.5 HC; V _{DO} = 1.653.6 B	SOT23-8	VCC1 • A1 • A2 • EN • GND • Y2 • Y1 • VCC
N1B	ADG3233BRM	AD	dsw	t _{PD} < 10.5 HC; V _{DD} = 1.653.6 B	MSOP-8	VCC2 • Y1 • Y2 • GND • EN • A2 • A1 • VCC

LFCSP-10 TDFN-10 TQFN-10

LFCSP-8 TDFN-8 5678

TDFN-6 678 321



LFCSP, TDFN, TQFN

Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6••16
#DBA	AD5304ACPZ	AD	DAC	4x8-pasp.; SPI/Microwire; V _{DD} =2.55.5B	LFCSP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
#DBB	AD5304BCPZ	AD	DAC	4x 8-pasp.; SPI/Microwire; V _{DD} = 2.55.5 B	LFCSP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
#DCA	AD5314ACPZ	AD	DAC	4x 10-pasp.; SPI/Microwire; V _{DD} = 2.55.5 B	LFCSP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
#DCB	AD5314BCPZ	AD	DAC	4x 10-pasp.; SPI/Microwire; V _{DD} = 2.55.5 B	LFCSP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
#DDA	AD5324ACPZ	AD	DAC	4x 12-pasp.; SPI/Microwire; V _{DD} = 2.55.5 B	LFCSP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
#DDB	AD5324BCPZ	AD	DAC	4x 12-pasp.; SPI/Microwire; V _{DD} = 2.55.5 B	LFCSP-10	VDD • VOUTA • VOUTB • VOUTC • REFIN • VOUTD • GND • DIN • SCLK • SYNC
+AFN	MAX1287ETA	MAX	ADC	2x12-pasp.; SPI/QSPI/Microwire; V _{DD} =2.73.6 B	TDFN-8	VDD • AIN1 • AIN2 • GND • REF • CNVST • DOUT • SCLK
+AFP	MAX1289ETA	MAX	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} =2.73.6 B	TDFN-8	VDD • AIN+ • AIN- • GND • REF • CNVST • DOUT • SCLK
+AFR	MAX1286ETA	MAX	ADC	2x12-pasp.; SPI/QSPI/Microwire; V _{DD} =4.55.5B	TDFN-8	VDD • AIN1 • AIN2 • GND • REF • CNVST • DOUT • SCLK
+AFT	MAX1288ETA	MAX	ADC	12-pasp.; SPI/QSPI/Microwire; V _{DD} =4.55.5 B	TDFN-8	VDD • AIN+ • AIN- • GND • REF • CNVST • DOUT • SCLK
151	ZX3CD1S1M832	ZETEX	pnp+ shd	V _{CEO} = 12 B; I _C =4 A; V _B =40 B; I _F =1.85 A	MLP-832	B • E • n. c. • A • F2 • K • K • C • C • F1
2S1	ZX3CD2S1M832	ZETEX	pnp+ shd	V _{CEO} =20 B; I _C =3.5 A; V _R =40 B; I _F =1.85 A	MLP-832	B • E • n. c. • A • F2 • K • K • C • C • F1
3S1	ZX3CD3S1M832	ZETEX	pnp+ shd	V _{CEO} =40B; I _C =3A; V _R =40B; I _F =1.85A	MLP-832	B • E • n. c. • A • F2 • K • K • C • C • F1
91A	ZXTD4591AM832	ZETEX	npn/pnp	V _{CB0} =40 B; I _{CN} =2 A; I _{CP} =1.5 A; P _D =1.5 B _T	MLP-832	B1 • E1 • B2 • E2 • F2 • C2 • C2 • C1 • C1 • F1
AAAM	MAX1595ETC50	MAX	cpreg	V _{IN} = 1.8 5.5 B; V _{DUT} = 5 B; I _{DUT} = 125 mA	TQFN-12	SHDN • IN • IN • GND • PGND • PGND • CXN • CXN • CXP • OUT • OUT • AOUT
AAAP	MAX1595ETC33	MAX	cpreg	V _{IN} = 1.8 5.5 B; V _{OUT} = 3.3 B; I _{OUT} = 125 MA	TQFN-12	SHDN • IN • IN • GND • PGND • PGND • CXN • CXN • CXP • OUT • OUT • AOUT
AAG	MAX4684ETB	MAX	asw	2xSPDT; R _{ON} < 0.5Om; V _{DD} = 1.85.5 B	TQFN-10	V+ • NO1 • COM1 • IN1 • NC1 • GND • NC2 • IN2 • COM2 • NO2
AAH	MAX4685ETB	MAX	asw	2xSPDT; R _{ON} < 0.8Om; V _{DD} = 1.85.5 B	TQFN-10	V+ • NO1 • COM1 • IN1 • NC1 • GND • NC2 • IN2 • COM2 • NO2
ABW	MAX1605ETT	MAX	vcon	V _{IN} = 2.45.5 B; V _{DUT} = 0.830 B; I _{CC} < 35 MKA	TDFN-6	SHDN • VCC • GND • LX • LIM • FB
ABX	MAX1833ETT30	MAX	vcon	V _{IN} = 1.55.5 B; V _{DUT} = 3.3 B; I _{CUT} < 150 mA	TDFN-6	SHDN • BATT • GND • LX • OUT • RST
AGS	MAX8880ETT	MAX	reg	LDO; V _{IN} = 2.512 B; V _{OUT} = 1.255B; I _{OUT} = 200 mA	TDFN-6	FB • GND • CUT • IN • SHDN • PCK
AJE	MAX1836ETT50	MAX	vcon	V _{IN} =4.524 B; V _{DUT} =5 B; I _{DUT} < 125 mA	TDFN-6	FB • GND • IN • LX • SHDN • OUT
AJF	MAX1837ETT50	MAX	vcon	V _{IN} =4.524B; V _{DIT} =5B; I _{DIT} < 250 mA	TDFN-6	FB • GND • IN • LX • SHDN • OUT
AJG	MAX1836ETT33	MAX	vcon	V _{IN} =4.524B; V _{DIJT} =3.3B; I _{DIJT} < 125 mA	TDFN-6	FB • GND • IN • LX • SHDN • OUT
AJH	MAX1837ETT33	MAX	vcon	V _{IN} =4.524B; V _{DUT} =3.3B; I _{DUT} <250 mA		FB • GND • IN • LX • SHDN • OUT
AJT	MAX5900NNETT	MAX	hscontr	V _{FF} =-1009B; I _{CC} <1.3 mA	TDFN-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OF
AJU	MAX5900AAETT	MAX	hscontr	V _{EE} =-1009B; I _{CC} < 1.3 mA; V _{CB} =200 mB	TDFN-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OF



TDFN-6

LFCSP-8 TDFN-8 5678 LFCSP-10 TDFN-10 TQFN-10

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Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6••16
AJV	MAX5900ABETT	MAX		V _{cc} =-1009B; I _{cc} <1.3 mA;	TDFN-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AUV	MAXOSUUABETT	MAX	hscontr	V _{CB} =300 mB	I DFN-0	VEE - DRAIN - GAIE - GND - PGOOD - ON/OFF
WLA	MAX5900ACETT	MAX	hscontr	V _{EE} =-1009В; I _{CC} <1.3 мА; V _{CB} =400 мВ	TDFN-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AJX	MAX5900LAETT	MAX	hscontr	V _{EE} =-1009B; I _{CC} <1.3 mA; V _{CB} =200 mB	TDFN-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AJY	MAX5900LBETT	MAX	hscontr	V _{EE} =-1009B; I _{CC} <1.3 мA; V _{CB} =300 мB	TDFN-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AJZ	MAX5900LCETT	MAX	hscontr	V _{EE} =-1009B; I _{CC} <1.3 mA; V _{CB} =400 mB	TDFN-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AKA	MAX5901NNETT	MAX	hscontr	V _{EE} =-1009B; I _{CC} <1.3 mA	TDFN-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AKB	MAX5901AAETT	MAX	hscontr	V _{EE} =-1009B; I _{CC} <1.3 мA; V _{CB} =200 мB	TDFN-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AKC	MAX5901ABETT	MAX	hscontr	V _{EE} =-1009B; I _{CC} <1.3 мA; V _{CB} =300 мB	TDFN-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AKD	MAX5901ACETT	MAX	hscontr	V _{EE} =-1009B; I _{CC} <1.3 мA; V _{CB} =400 мB	TDFN-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AKE	MAX5901LAETT	MAX	hscontr	V _{EE} =-1009B; I _{CC} <1.3 мA; V _{CB} =200 мB	TDFN-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AKF	MAX5901LBETT	MAX	hscontr	V _{EE} =-1009B; I _{CC} <1.3 мA; V _{CB} =300 мB	TDFN-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AKG	MAX5901LCETT	MAX	hscontr	V _{EE} =-1009B; I _{CC} <1.3 мA; V _{CB} =400 мB	TDFN-6	VEE • DRAIN • GATE • GND • PGOOD • ON/OFF
AKH	MAX5902NNETT	MAX	hscontr	V _S =+9+72B; I _{CC} <2 мA	TDFN-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AKI	MAX5902AAEUT	MAX	hscontr	$V_S = +9+72B$; $I_{CC} < 2 \text{ mA}$; $V_{CB} = 300 \text{ mB}$	TDFN-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AKJ	MAX5902ABETT	MAX	hscontr	$V_S = +9+72B$; $I_{CC} < 2 \text{ mA}$; $V_{CB} = 400 \text{ mB}$	TDFN-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AKK	MAX5902ACETT	MAX	hscontr	V _S =+9+72B; I _{CC} <2 mA; V _{CB} =500 mB	TDFN-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AKL	MAX5902LAETT	MAX	hscontr	$V_S = +9+72B$; $I_{CC} < 2 \text{ mA}$; $V_{CB} = 300 \text{ mB}$	TDFN-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AKM	MAX5902LBETT	MAX	hscontr	$V_S = +9 + 72B$; $I_{CC} < 2 \text{ mA}$; $V_{CB} = 400 \text{ mB}$	TDFN-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AKN	MAX5902LCETT	MAX	hscontr	$V_S = +9+72B$; $I_{CC} < 2 \text{ mA}$; $V_{CB} = 500 \text{ mB}$	TDFN-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AKO	MAX5903NNETT	MAX	hscontr	V _S =+9+72B; I _{CC} <2 mA	TDFN-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AKP	MAX5903AAETT	MAX	hscontr	$V_S = +9+72B$; $I_{CC} < 2 \text{ mA}$; $V_{CB} = 300 \text{ mB}$	TDFN-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AKQ	MAX5903ABETT	MAX	hscontr	$V_S = +9 + 72B$; $I_{CC} < 2 \text{ mA}$; $V_{CB} = 400 \text{ mB}$	TDFN-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AKR	MAX5903ACETT	MAX	hscontr	V _S =+9+72B; I _{CC} <2 mA; V _{CB} =500 mB	TDFN-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AKS	MAX5903LAETT	MAX	hscontr	V _S =+9+72B; I _{CC} <2 mA; V _{CB} =300 mB	TDFN-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AKT	MAX5903LBETT	MAX	hscontr	V _S =+9+72B; I _{CC} <2 mA; V _{CB} =400 mB	TDFN-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AKU	MAX5903LCETT	MAX	hscontr	$V_S = +9+72B$; $I_{CC} < 2 \text{ mA}$; $V_{CB} = 500 \text{ mB}$	TDFN-6	VS • DRAIN • GATE • GND • PGOOD • ON/OFF
AKV	MAX5048AATT	MAX	drv	КМОП-вход; V _{CC} = 412.6 В; I _{DUT} < 7.6/1.3 А	TDFN-6	V+•P_OUT•N_OUT•GND•IN-•IN+
AKW	MAX5048BATT	MAX	drv	ТТЛ-вход; V _{CC} =412.6 В; I _{DUT} < 7.6/1.3A	TDFN-6	V+•P_OUT•N_OUT•GND•IN-•IN+
BS1	ZX3CDBS1M832	ZETEX	shd	V _{CEO} = 20B; I _C = 4.5 A; V _R = 40 B; I _F = 1.85 A	MLP-832	B • E • n. c. • A • F2 • K • K • C • C • F1
C01	ZXMC3AM832		nMOS/p MOS	V _{DS} = 30 B; I _{DN} = 2.9 A; I _{DP} = 2.1 A; R _{DS(on)N} < 0.18 OM; R _{DS(on)P} < 0.33 OM	MLP-832	S1 • G1 • S2 • G2 • F2 • D2 • D2 • D1 • D1 • F1
D11	ZXTD1M832	ZETEX	pnp x2	V _{CE0} = 12 B, I _C = 4A, P _D = 1.5 B _T	MLP-832	B1 • E1 • B2 • E2 • F2 • C2 • C2 • C1 • C1 • F1
D22	ZXTD2M832	ZETEX	pnp x2	V _{CE0} = 20 B; I _C = 3.5A; P _D = 1.5 B _T	MLP-832	B1 • E1 • B2 • E2 • F2 • C2 • C2 • C1 • C1 • F1
D33	ZXTD3M832	ZETEX	pnp x2	V _{CE0} = 40 B; I _C = 3A; P _D = 1.5 B _T	MLP-832	B1 • E1 • B2 • E2 • F2 • C2 • C2 • C1 • C1 • F1
DA1	ZXTDA1M832	ZETEX	npn/pnp	$V_{CEDN} = 15 B$; $V_{CEDP} = 12 B$; $I_{CN} = 4.5 A$; $I_{CP} = 4 A$; $P_D = 1.5 B T$	MLP-832	B1 • E1 • B2 • E2 • F2 • C2 • C2 • C1 • C1 • F1
DAA	ZXTDAM832	ZETEX	npn x2	V _{CF0} = 15 B; I _C = 4.5 A; P _D = 1.5 B _T	MLP-832	B1 • E1 • B2 • E2 • F2 • C2 • C2 • C1 • C1 • F1

LFCSP-16

LFCSP-10 TDFN-10 TQFN-10 6 7 8 9 10



Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4•5•6••16
DB2	ZXTDB2M832	ZETEX	npn/pnp	$V_{CEON} = 20B$; $V_{CEOP} = 20B$; $I_{CN} = 4.5A$; $I_{CP} = 3.5A$; $P_D = 1.5BT$	MLP-832	B1 • E1 • B2 • E2 • F2 • C2 • C2 • C1 • C1 • F1
DBB	ZXTDBM832	ZETEX	npn x2	V _{CE0} =20B; I _C =4.5A; P _D =1.5B _T	MLP-832	B1 • E1 • B2 • E2 • F2 • C2 • C2 • C1 • C1 • F1
DC3	ZXTDC3M832	ZETEX	npn/pnp	$V_{CEON} = 50 B$; $V_{CEOP} = 40 B$; $I_{CN} = 4 A$; $I_{CP} = 3 A$; $P_D = 1.5 B T$	MLP-832	B1 • E1 • B2 • E2 • F2 • C2 • C2 • C1 • C1 • F1
DCC	ZXTDCM832	ZETEX	npn x2	V _{CE0} =50B; I _C =4A; P _D =1.5BT	MLP-832	B1 • E1 • B2 • E2 • F2 • C2 • C2 • C1 • C1 • F1
DE4	ZXTDE4M832		npn/pnp	$V_{CEON} = 80 B$; $V_{CEOP} = 70 B$; $I_{CN} = 3.5 A$; $I_{CP} = 2.5 A$; $P_D = 1.5 B r$		B1 • E1 • B2 • E2 • F2 • C2 • C2 • C1 • C1 • F1
DNA	ZXMN2AM832			$V_{DS} = 20B$; $I_D = 13A$; $P_D = 1.5B\tau$; $R_{DS[on]} < 0.3 \text{ OM}$		S1 • G1 • S2 • G2 • F2 • D2 • D2 • D1 • D1 • F1
DNB	ZXMN3AM832	ZETEX	nMOS x2	V _{DS} = 30B; I _D = 13A; P _D = 1.5BT; R _{DS[on]} < 0.18 Om	MLP-832	S1 • G1 • S2 • G2 • F2 • D2 • D2 • D1 • D1 • F1
DPA	ZXMP62M832	ZETEX	pMOS x2	$V_{DS} = 20B$; $I_D = 1.3A$; $P_D = 1.5B\tau$; $R_{DS[on]} < 0.9 \text{ CM}$	MLP-832	S1 • G1 • S2 • G2 • F2 • D2 • D2 • D1 • D1 • F1
J5A	AD8314ACP	AD	LA	$f_{BD} = 0.12.7\Gamma\Gamma\mu; P_D = 30 \text{ MBT};$ $V_{DD} = 2.75.5 \text{ B}$	LFCSP-8	RFIN • ENBL • VSET • FLTR • COMM • V UP • V DN • VPOS
J7A	AD8315ACP	AD	LA	$f_{BD} = 0.12.5\Gamma\Gamma\mu; P_D = 60 \text{ mBT}; V_{DD} = 2.75.5 \text{ B}$	LFCSP-8	RFIN • ENBL • VSET • FLTR • COMM • n. c. • VAPC • VPOS
J8A	AD8316ACP	AD	LA	$f_{BD} = 0.12.5\Gamma\Gamma \mu; P_D = 60 \text{ mB} \tau; V_{DD} = 2.75.5 \text{ B}$	LFCSP-16	RFIN ●ENBL●VSET ●FLTR ●n. c. ● BSEL● FLT2 ● n. c. ● OUT2 ● COMM ● OUT1 ● VPOS ● n c. ● COMM ● n. c. ●n. c.
LFA	ADP3335ACP-1.8	AD	reg	LDO; V _{IN} = 2.612B; I _{DUT} = 500 mA; V _{DUT} = 1.8 B	LFCSP-8	OUT • OUT • OUT • GND • NR • SD • IN • IN
LFC	ADP3335ACP-2.5	AD	reg	LDO; V _{IN} = 2.612B; I _{DUT} = 500 mA; V _{DUT} = 2.5 B	LFCSP-8	OUT • OUT • OUT • GND • NR • SD • IN • IN
LFD	ADP3335ACP-2.85	AD	reg	LDO; V _{IN} = 2.612B; I _{DUT} = 500 mA; V _{DUT} = 2.85 B	LFCSP-8	OUT • OUT • OUT • GND • NR • SD • IN • IN
LFE	ADP3335ACP-3.3	AD	reg	LDO; V _{IN} = 2.612B; I _{OUT} = 500 мA; V _{OUT} = 3.3 B	LFCSP-8	OUT • OUT • OUT • GND • NR • SD • IN • IN
LFF	ADP3335ACP-5	AD	reg	LDO; V _{IN} = 2.612B; I _{OUT} = 500 mA; V _{OUT} = 5 B	LFCSP-8	OUT • OUT • OUT • GND • NR • SD • IN • IN
MSA	ZXMNS3BM832	ZETEX	nMOS+ shd	$V_{DS} = 30B$; $I_D = 2A$; $V_R = 40B$; $I_F = 1.85A$	MLP-832	S • G • n. c. • A • F2 • K • K • D • D • F1
MSB	ZXMPS62M832	ZETEX	pMOS+ shd	V _{DS} = 20B; I _D = 1.3 A; V _R = 40 B; I _F = 1.85 A	MLP-832	S•G•n. c. •A•F2•K•K•D•D•F1

UCSP-4 UCSP-5 UCSP-6 WLCSP-5 WLCSP-6 WCSP-8











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UCSP, WCSP...

Код	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4••12
AAA	MAX2240EBL	MAX	amp	$V_{CC} = 2.75 B$; $f_P = 2.42.5 \Gamma \Gamma U_i I_{CC} \le 155 \text{ mA}$	UCSP-9	D0 • D1 • BIAS • RFOUT • SHDN • GND1 • GND2 • VCC • RFIN
AAA	MAX6400BS22	MAX	mrc	$V_{TR} = 2.2 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 1 \text{ MKA}$	UCSP-4	GND • VCC • MR • RESET
AAB	MAX1820ZEBC	MAX	dodo	V _{IN} = 2.65.5B; V _{OUT} = 0.43.4B; I _{OUT} = 600 mA	UCSP-10	SKIP • COMP • CUT • REF • GND • PGND • LX • BATT • SHDN • SYNC
AAB	MAX2374EBT	MAX	amp	SiGe; $V_{CC} = 2.75.5 B$; $f_P = 7501000 M\Gamma u$; $I_{CC} < 10.5 MA$	UCSP-6	GAIN • LNAIN • GND • BIAS • LNACUT • VCC
AAB	MAX6400BS23	MAX	mrc	V _{TR} = 2.32 B; V _{DD} = 1.25.5 B; I _{CC} < 1 mkA	UCSP-4	GND • VCC • MR • RESET
AAC	MAX1819EBL20	MAX	reg	LDO; V _{IN} = 2.5 5.5 B; V _{OUT} = 2.0/1.25 5 B; I _{OUT} = 500 mA	UCSP-6	IN • POK • SHDN • GND • SET • OUT
AAC	MAX1821EBC	MAX	dcdc	V _{IN} = 2.65.5B; V _{OUT} = 1.255.5B; I _{OUT} = 600 мA	UCSP-10	SKIP • COMP • FB • REF • GND • PGND • LX • BATT • SHDN • SYNC
AAC	MAX6400BS24	MAX	mrc	V _{TR} = 2.4B; V _{DD} = 1.25.5B; I _{CC} < 1 mrA	UCSP-4	GND • VCC • MR • RESET
AAD	MAX1819EBL25	MAX	reg	LDO; V _{IN} =2.55.5B; V _{OUT} =2.5/1.255B; I _{OUT} =500mA	UCSP-6	IN • POK • SHDN • GND • SET • OUT
AAD	MAX6400BS25	MAX	mrc	V _{TR} = 2.5B; V _{DD} = 1.25.5B; I _{CC} < 1 mrA	UCSP-4	GND • VCC • MR • RESET
AAE	MAX1819EBL33	MAX	reg	LDO; V _{IN} = 2.5 5.5 B; V _{DUT} = 3.3/1.25 5 B; I _{DUT} = 500 mA	UCSP-6	IN • POK • SHDN • GND • SET • OUT
AAE	MAX2242EBC	MAX	amp	$V_{CC} = 2.73.6 \text{ B}; f_p = 2.42.5 \Gamma \Gamma u; I_{CC} < 335 \text{ mA}$	UCSP-12	GND • VCC2 • GND • VCC1 • RF_OUT • PD_OUT • n. c. • GND • BIAS • SHDN • VCCB • RF_IN
AAE	MAX2648EBT	MAX	amp	SiGe; V _{CC} = 2.73.6 B; f _P =5000+R[1841]C6000 ΜΓц; I _{CC} < 18 мA	UCSP-6	RFIN • GND • GND • VCC • GND • RFOUT
AAE	MAX6400BS26	MAX	mrc	V _{TR} = 2.63 B; V _{DD} = 1.25.5 B; I _{CC} < 1 mrA	UCSP-4	GND • VCC • MR • RESET
AAF	MAX1819EBL50	MAX	reg	LDO; V _{IN} = 2.5 5.5 B; V _{DUT} = 5.0/1.25 5 B; I _{DUT} = 500 mA	UCSP-6	IN • POK • SHDN • GND • SET • OUT
AAF	MAX4684EBC	MAX	asw	2 x SPDT; R _{ON} < 0.5 Om; V _{DD} = 1.85.5 B	UCSP-10	NC2 • IN2 • COM2 • NO2 • GND • V+ • NC1 • IN1 • COM1 • NO1
AAF	MAX6400BS27	MAX	mrc	V _{TR} = 2.7B; V _{DD} = 1.25.5B; I _{CC} < 1 мкA	UCSP-4	GND • VCC • MR • RESET
AAG	MAX1819EBL18	MAX	reg	LDO; V _{IN} = 2.5 5.5 B; V _{DUT} = 1.8/1.25 5 B; I _{DUT} = 500 mA	UCSP-6	IN • POK • SHDN • GND • SET • OUT
AAG	MAX4685EBC	MAX	asw	2 x SPDT; R _{ON} < 0.8 Om; V _{DD} = 1.85.5 B	UCSP-10	NC2 • IN2 • COM2 • NO2 • GND • V+ • NC1 • IN1 • COM1 • NO1
AAG	MAX6400BS28	MAX	mrc	V _{TR} = 2.8 B; V _{DD} = 1.25.5 B; I _{CC} < 1 mrA	UCSP-4	GND • VCC • MR • RESET
AAH	MAX1819EBL15	MAX	reg	LDO; V _{IN} = 2.5 5.5 B; V _{DUT} = 1.5/1.25 5 B; I _{DUT} = 500 mA	UCSP-6	IN • POK • SHDN • GND • SET • OUT
AAH	MAX2307EBC	MAX	amp	V _{CC} = 2.84.2 В; ¼= 887925 МГц; I _{CC} < 38 мА	UCSP-12	VCC • VCC MIXP • VCC MIXM • GND • LOIN/SHDN • n. c. • GC • RF_OUT • GND • IFINP • IFINM • SHDN
AAH	MAX6400BS29	MAX	mrc	$V_{TR} = 2.93 \text{ B}; V_{DD} = 1.25.5 \text{ B}; I_{CC} \le 1 \text{ MKA}$	UCSP-4	GND • VCC • MR • RESET
AAI	MAX4686EBT	MAX	asw	SPST; R _{CN} < 3.5 Om; V _{DD} = 1.85.5 B	UCSP-6	NO • I.C. • COM • GND • IN • V+
AAI	MAX6400BS30	MAX	mrc	$V_{TR} = 3.0 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} < 1 \text{ MKA}$	UCSP-4	GND • VCC • MR • RESET
AAJ	MAX2383BC	MAX	amp	V _{CC} = 2.73 B ; f _P = 19201980МГц; I _{CC} < 44мА	UCSP-12	LO+/LO_EN • VCC • DROUT • GND • LO-/SHDN • n. c. • GC • DRIN • IFIN- • IFIN+ • RF_OUT • GND
AAJ	MAX4292EBL	MAX	dOA	R-R; V_{DD} = 1.85.5/±0.9±2.75 B; f_{BD} = 500 κΓι; V_{DSI} < 2.5 мB	UCSP-8	OUTA • VCC • OUTB • INB- • INB+ • VEE • INA+ • INA-
AAJ	MAX4687EBT	MAX	asw	SPST; R _{CN} < 3.5 Om; V _{DD} = 1.85.5 B	UCSP-6	NC ● I.C. ● COM ● GND ● IN ● V+
AA.J	MAX6400BS31	MAX	mrc	$V_{TR} = 3.08 \text{ B}; V_{DD} = 1.25.5 \text{ B}; I_{CC} \le 1 \text{ m/s}A$	UCSP-4	GND • VCC • MR • RESET
AAK	MAX4688EBT	MAX	asw	SPDT; R _{ON} < 3.5 Om; V _{DD} = 1.85.5 B	UCSP-6	NO • COM • NC • GND • IN • V+

WCSP-8 **1**234 8765





UCSP-12



UCSP-10









				UCSP-12 UCSP-10 UCSP-		CSP-8
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Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1 • 2 • 3 • 4 • • 12
AAK	MAX6410BS33	MAX	vd	V _{TB} = 3.30B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mkA	UCSP-4	GND • VCC • MR • OUT
AAL	MAX1820YEBC	MAX	dcdc	V _{IN} = 2.65.5B; V _{OUT} = 0.43.4B; f _{CUX} = 19.8МГц; I _{CUT} = 600 мА	UCSP-10	SKIP • COMP • OUT • REF • GND • PGND • LX • BATT • SHDN • SYNC
AAL	MAX4696EBT	MAX	asw	SPST; R _{DN} < 40 O _M ; V _{DD} = 2.05.5B	UCSP-6	NO • COM • COM • GND • IN • V+
AAL	MAX6410BS34	MAX	vd	V _{TB} = 3.40B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mkA	UCSP-4	GND • VCC • MR • OUT
AAM	MAX1820XEBC	MAX	dcdc	V_{IN} = 2.65.5B; V_{OUT} = 0.43.4B; f_{CUK} = 13MFu; I_{OUT} = 600 mA	UCSP-10	SKIP • COMP • OUT • REF • GND • PGND • LX • BATT • SHDN • SYNC
AAM	MAX4697EBT	MAX	asw	SPST; R _{DN} < 40 OM; V _{DD} = 2.05.5B	UCSP-6	NC • COM • COM • GND • IN • V+
AAM	MAX6410BS35	MAX	vd	V _{TR} = 3.50B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AAN	MAX4698EBT	MAX	asw	SPDT; R _{DN} < 40 OM; V _{DO} = 2.05.5 B	UCSP-6	NO • COM • NC • GND • IN • V+
AAN	MAX6410BS36	MAX	vd	V _{TR} =3.60B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	UCSP-4	GND • VCC • MR • OUT
AAO	MAX6410BS37	MAX	vd	V _{IR} =3.70B; V _{DD} =1.25.5B; I _{CC} <1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AAP	MAX6410BS38	MAX	νd	V _{IR} =3.80B; V ₀₀ =1.25.5B; I _{CC} <1.75 mrA	UCSP-4	GND • VCC • MR • OUT
AAQ	MAX6410BS39	MAX	vd	V _{TR} = 3.90B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
AAR	MAX6410BS40	MAX	vd	V _{TR} = 4.00B; V ₀₀ = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AAS	MAX6410BS41	MAX	νd	V _{IR} =4.10B; V _{DO} =1.25.5B; I _{CC} <1.75 mKA	UCSP-4	GND • VCC • MR • CUT
AAT	MAX6410BS42	MAX	vd	V _{IB} = 4.20B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AAU	MAX6410BS43	MAX	vd	V _{IR} =4.30B; V ₀₀ =1.25.5B; I _{CC} <1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AAV	MAX1821XEBC	MAX	dcdc	V_{IN} = 2.65.5B; V_{OUT} = 1.255.5B; f_{CLK} = 13 MF $_{II}$; I_{OUT} = 600 mA	UCSP-10	SKIP • COMP • FB • REF • GND • PGND • LX • BATT • SHDN • SYNC
AAV	MAX6410BS44	MAX	vd	V _{TR} = 4.38B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AAW	MAX4323EBT	MAX	OA	R-R; V _{DD} =2.46.5/±1.2±3.25B; f _{BD} =5MFu; V _{DSI} <3.5MB	UCSP-6	VEE • OUT • VCC • SHDN • IN- • IN+
AAW	MAX6410BS45	MAX	νd	V _{IR} =4.50B; V _{DO} =1.25.5B; I _{CC} <1.75 mKA	UCSP-4	GND • VCC • MR • CUT
AAX	MAX6410BS46	MAX	vd	V _{TR} = 4.63B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
AAY	MAX6411BS33	MAX	vd	V _{TR} = 3.30B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AAY	MAX985EBT	MAX	стр	$R-R$; $V_{OSI} < \pm 7 \text{ mB}$; $V_{CC} = 2.55.5 \text{ B}$; $I_{CC} < 24 \text{ mkA}$	UCSP-6	VEE • OUT • VCC • n. c. • IN- • IN+
AAZ	MAX6411BS34	MAX	vd	V _{TR} = 3.40B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AAZ	MAX9039BEBT	MAX		R-R; $V_{CSI} \le \pm 7$ mB; $V_{CC} = 2.55.5$ B; $V_{REF} = 1.230$ B; $I_{CC} \le 72$ mKA	UCSP-6	VEE • OUT • VCC • REF • IN- • IN+
ABA	MAX6411BS35	MAX	vd	V _{TR} = 3.50B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • OUT
ABB	MAX6411BS36	MAX	vd	V _{TR} = 3.60B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
ABC	MAX6411BS37	MAX	vd	V _{TR} = 3.70B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
ABD	MAX6411BS38	MAX	vd	V _{TR} = 3.80B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
ABE	MAX6411BS39	MAX	vd	V _{TR} = 3.90B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
ABF	MAX6411BS40	MAX	vd	V _{TR} = 4.00B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
ABG	MAX6411BS41	MAX	vd	V _{TR} = 4.10B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
ABH	MAX6411BS42	MAX	vd	V _{TR} = 4.20B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
ABI	MAX6411BS43	MAX	vd	V _{TR} = 4.30 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
ABJ	MAX6411BS44	MAX	vd	V _{TR} = 4.38 B; V _{DO} = 1.25.5 B; I _{CC} < 1.75 mrA	UCSP-4	GND • VCC • MR • OUT
ABK	MAX6411BS45	MAX	vd	V _{TR} = 4.50B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mkA	UCSP-4	GND • VCC • MR • OUT
ABL	MAX6411BS46	MAX	vd	V _{TR} = 4.63B; V _{DO} = 1.25.5B; I _{CC} < 1.75 m/A	UCSP-4	GND • VCC • MR • OUT
ABM	MAX6401BS22	MAX	mrc	V _{TB} =2.2B; V _{DD} =1.25.5B; I _{CC} <1 mKA	UCSP-4	GND • VCC • MR • RESET
ABN	MAX6401BS23	MAX	mrc	V _{TR} = 2.32B; V _{DO} = 1.25.5B; I _{CC} < 1 mKA	UCSP-4	GND • VCC • MR • RESET
ABO	MAX6401BS24	MAX	mrc	V _{TB} = 2.4 B; V _{DD} = 1.25.5 B; I _{CC} < 1 mkA	UCSP-4	GND • VCC • MR • RESET
ABP	MAX6401BS25	MAX	mrc	V _{TR} = 2.5 B; V _{DD} = 1.25.5 B; I _{CC} < 1 mkA	UCSP-4	GND • VCC • MR • RESET
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Код	Типономинал	Б	ф		Особенности		Корпус	Ц: 1•2•3•4••12
BQ	MAX6401BS26	MAX	mrc	V _{TR} = 2.63 B; V _{DD} = 1.2	5.5B; I _{CC} <1 мкA		UCSP-4	GND • VCC • MR • RESET
BR	MAX6401BS27	MAX	mrc	V _{TR} = 2.7B; V _{DO} = 1.25	.5В; I _{CC} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ABS	MAX6401BS28	MAX	mrc	V _{TR} = 2.8B; V _{DD} = 1.25	.5В; I _{CC} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ABT	MAX6401BS29	MAX	mrc	V _{TR} = 2.93 B; V _{DD} = 1.2	5.5B; I _{CC} <1 mkA		UCSP-4	GND • VCC • MR • RESET
ABU	MAX6401BS30	MAX	mrc	V _{TR} = 3.0B; V _{DO} = 1.25	.5В; I _{CC} <1 мкА		UCSP-4	GND • VCC • MR • RESET
ABV	MAX6401BS31	MAX	mrc	V _{TR} = 3.08 B; V _{DD} = 1.2	5.5B; I _{CC} < 1 мкA		UCSP-4	GND • VCC • MR • RESET
ABW	MAX6402BS22	MAX	mrc	V _{TR} = 2.2B; V _{DO} = 1.25	.5В; I _{CC} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ABX	MAX6402BS23	MAX	mrc	V _{TR} = 2.32 B; V _{DD} = 1.2	5.5B; l _{CC} <1 мкА		UCSP-4	GND • VCC • MR • RESET
ABY	MAX6402BS24	MAX	mrc	V _{TR} = 2.4B; V _{DD} = 1.25	.5В; I _{CC} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ABZ	MAX6402BS25	MAX	mrc	V _{TR} = 2.5B; V _{DO} = 1.25	.5B; I _{CC} < 1 мкA		UCSP-4	GND • VCC • MR • RESET
ACA	MAX6402BS26	MAX	mrc	V _{TR} = 2.63 B; V _{DD} = 1.2	5.5B; I _{CC} <1 мкА		UCSP-4	GND • VCC • MR • RESET
ACB	MAX6402BS27	MAX	mrc	V _{TR} = 2.7B; V _{DD} = 1.25	.5B; I _{CC} < 1 мкA		UCSP-4	GND • VCC • MR • RESET
ACC	MAX6402BS28	MAX	mrc	V _{TR} = 2.8B; V _{DO} = 1.25	.5В; I _{CC} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ACD	MAX6402BS29	MAX	mrc	V _{TR} = 2.93 B; V _{DD} = 1.2	5.5B; l _{CC} <1 мкA		UCSP-4	GND • VCC • MR • RESET
4CE	MAX6402BS30	MAX	mrc	V _{TR} = 3.0B; V _{DD} = 1.25	.5B; I _{CC} < 1 мкA		UCSP-4	GND • VCC • MR • RESET
ACF	MAX6402BS31	MAX	mrc	V _{TR} = 3.08 B; V _{DD} = 1.2	5.5B; I _{CC} <1 мкА		UCSP-4	GND • VCC • MR • RESET
ACG	MAX6403BS33	MAX	mrc	V _{TR} = 3.3B; V _{DO} = 1.25	.5В; I _{CC} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ACH	MAX6403BS34	MAX	mrc	V _{TR} = 3.4B; V _{DO} = 1.25	.5В; I _{CC} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ACI	MAX6403BS35	MAX	mrc	V _{TR} = 3.5B; V _{DO} = 1.25	.5В; I _{CC} <1 мкА		UCSP-4	GND • VCC • MR • RESET
4CJ	MAX6403BS36	MAX	mrc	V _{TR} = 3.6B; V _{DO} = 1.25	.5В; I _{CC} <1 мкА		UCSP-4	GND • VCC • MR • RESET
ACK	MAX6403BS37	MAX	mrc	V _{TR} = 3.7B; V _{DO} = 1.25	5B; I _{CC} < 1 mkA		UCSP-4	GND • VCC • MR • RESET
ACL	MAX6403BS38	MAX	mrc	V _{TR} = 3.8B; V _{DO} = 1.25	.5В; I _{CC} <1 мкА		UCSP-4	GND • VCC • MR • RESET
ACM	MAX6403BS39	MAX	mrc	V _{TR} = 3.9B; V _{DO} = 1.25	.5В; I _{CC} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ACN	MAX6403BS40	MAX	mrc	V _{TR} = 4.0B; V _{DO} = 1.25	.5В; I _{CC} <1 мкА		UCSP-4	GND • VCC • MR • RESET
4CO	MAX6403BS41	MAX	mrc	V _{TR} = 4.1B; V _{DO} = 1.25	.5В; I _{CC} <1 мкА		UCSP-4	GND • VCC • MR • RESET
ACP	MAX6403BS42	MAX	mrc	V _{TB} = 4.2B; V _{DO} = 1.25	.5В; I _{сс} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ACQ	MAX6403BS43	MAX	mrc	V _{TR} = 4.3B; V _{DO} = 1.25	.5В; I _{CC} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ACR	MAX6403BS44	MAX	mrc	V _{TR} = 4.38 B; V _{DD} = 1.2	5.5B; I _{cc} <1 мкА		UCSP-4	GND • VCC • MR • RESET
ACS	MAX6403BS45	MAX	mrc	V _{TR} = 4.5B; V _{DO} = 1.25	.5B; I _{CC} < 1 мкA		UCSP-4	GND • VCC • MR • RESET
ACT	MAX6403BS46	MAX	mrc	V _{TR} = 4.63 B; V _{DD} = 1.2			UCSP-4	GND • VCC • MR • RESET
ACU	MAX6404BS33	MAX	mrc	V _{TR} = 3.3B; V _{DO} = 1.25			UCSP-4	GND • VCC • MR • RESET
ACV	MAX6404BS34	MAX	mrc	V _{TR} = 3.4B; V _{DO} = 1.25	5В; I _{CC} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ACW	MAX6404BS35	MAX	mrc	V _{TR} = 3.5B; V _{DO} = 1.25	.5В; I _{CC} <1 мкА		UCSP-4	GND • VCC • MR • RESET
4CX	MAX4372TEBT	MAX	CSA	V ₀₀ = 2.728B; Gain = 2	:0; I _{CC} < 1.9мА		UCSP-5	VCC • GND • OUT • RS- • RS+
4CX	MAX6404BS36	MAX	mrc	V _{TR} = 3.6B; V _{DO} = 1.25	.5В; I _{CC} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ACY	MAX4372FEBT	MAX	CSA	V ₀₀ =2.728B; Gain=5	Ю; I _{CC} < 1.9мА		UCSP-5	VCC • GND • OUT • RS- • RS+
ACY	MAX6404BS37	MAX	mrc	V _{TR} = 3.7B; V _{DO} = 1.25	.5В; I _{CC} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ACZ	MAX4372HEBT	MAX	CSA	V _{DD} =2.728B; Gain=1	V-10-10-10-10-10-10-10-10-10-10-10-10-10-		UCSP-5	VCC • GND • OUT • RS- • RS+
ACZ	MAX6404BS38	MAX	mrc	V _{TR} = 3.8B; V _{DO} = 1.25	.5В; I _{CC} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ADA	MAX6404BS39	MAX	mrc	V _{TR} = 3.9B; V _{DO} = 1.25	.5В; I _{CC} < 1 мкА		UCSP-4	GND • VCC • MR • RESET
ADB	MAX6404BS40	MAX	mrc	V _{TR} = 4.0B; V _{DD} = 1.25	5B; I _{CC} < 1 мкA		UCSP-4	GND • VCC • MR • RESET
ADC	MAX6404BS41	MAX	mrc	V _{TR} = 4.1B; V _{DO} = 1.25			UCSP-4	GND • VCC • MR • RESET
ADD	MAX6404BS42	MAX	mrc	V _{IR} = 4.2B; V _{DO} = 1.25			UCSP-4	GND • VCC • MR • RESET
ADE	MAX6404BS43	MAX	mrc	V _{TR} = 4.3B; V _{DD} = 1.25			UCSP-4	GND • VCC • MR • RESET







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Kon	Типономинал	Б	Ф	Особенности	Корпус	Ц: 1•2•3•4••12
	MAX6404BS44	-		V _{TB} = 4.38B; V _{DD} = 1.25.5B; I _{CC} < 1 m/kA	UCSP-4	GND • VCC • MR • RESET
1073	MAX6404BS45	MAX		V _{TB} = 4.5B; V _{DD} = 1.25.5B; I _{CC} < 1 mkA	0.00	GND • VCC • MR • RESET
	MAX6404BS46	MAX	mrc	V _{TB} =4.63B; V _{DD} =1.25.5B; I _{CC} <1 MKA	UCSP-4	GND • VCC • MR • RESET
	MAX6405BS33				UCSP-4	GND • VCC • MR • RESET
77.5	MAX6405BS34			V _{TR} =3.3B; V _{DD} =1.25.5B; I _{CC} <1 mKA	UCSP-4	GND • VCC • MR • RESET
	MAX6405BS35	MAX		V _{IR} =3.4B; V _{DD} =1.25.5B; I _{CC} <1 mrA	UCSP-4	GND • VCC • MR • RESET
	MAX6405BS36	MAX		V _{TR} =3.5B; V _{DD} =1.25.5B; I _{CC} <1 mKA		GND • VCC • MR • RESET
			-	V _{TR} = 3.6 B; V _{DD} = 1.25.5 B; I _{CC} < 1 mrA	UCSP-4	
	MAX6405BS37	MAX		V _{IR} =3.7B; V _{DD} =1.25.5B; I _{CC} <1 mKA		GND • VCC • MR • RESET
_	MAX6405BS38			V _{TR} = 3.8 B; V _{DD} = 1.25.5 B; I _{CC} < 1 mrA		GND • VCC • MR • RESET
	MAX6405BS39	MAX		V _{TR} = 3.9 B; V _{DD} = 1.25.5 B; I _{CC} < 1 mrA	UCSP-4	GND • VCC • MR • RESET
	MAX6405BS40	MAX		V _{TR} =4.0 B; V _{DD} =1.25.5 B; I _{CC} < 1 mKA	UCSP-4	GND • VCC • MR • RESET
_	MAX6405BS41	MAX		V _{TR} = 4.1 B; V _{DD} = 1.25.5 B; I _{CC} < 1 mKA		GND • VCC • MR • RESET
_	MAX6405BS42	MAX		V _{TR} =4.2 B; V _{DD} =1.25.5 B; I _{CC} < 1 mKA	UCSP-4	GND • VCC • MR • RESET
	MAX6405BS43	MAX		V _{TR} =4.3 B; V _{DD} =1.25.5 B; I _{CC} < 1 мкA	UCSP-4	GND • VCC • MR • RESET
	MAX6405BS44	MAX		V _{TR} =4.38B; V _{DO} =1.25.5B; I _{CC} <1 mKA		GND • VCC • MR • RESET
	MAX6405BS45	MAX		V _{TR} =4.5 B; V _{DD} =1.25.5 B; I _{CC} < 1 мкA	UCSP-4	GND • VCC • MR • RESET
	MAX6405BS46	MAX		V _{TR} = 4.63B; V _{DD} = 1.25.5B; I _{CC} < 1 mKA	UCSP-4	GND • VCC • MR • RESET
ADW	MAX6406BS22	MAX		V _{TR} = 2.20B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • OUT
ADX	MAX6406BS23	MAX		$V_{TR} = 2.32B$; $V_{00} = 1.25.5B$; $I_{CC} < 1.75 \text{ mKA}$	UCSP-4	GND • VCC • MR • OUT
ADY	MAX6406BS24	MAX	vd	$V_{TR} = 2.40B$; $V_{DO} = 1.25.5B$; $I_{CC} < 1.75 \text{ mKA}$	UCSP-4	GND • VCC • MR • OUT
ADZ	MAX6406BS25	MAX	vd	$V_{TR} = 2.50B$; $V_{DO} = 1.25.5B$; $I_{CC} \le 1.75 \text{ mKA}$	UCSP-4	GND • VCC • MR • OUT
AEA	MAX6406BS26	MAX	vd	$V_{TR} = 2.63 \text{ B}; V_{OO} = 1.25.5 \text{ B}; I_{CC} < 1.75 \text{ mKA}$	UCSP-4	GND • VCC • MR • OUT
AEB	MAX6406BS27	MAX	vd	$V_{TR} = 2.70 \text{ B}; V_{DO} = 1.25.5 \text{ B}; I_{CC} \le 1.75 \text{ mKA}$	UCSP-4	GND • VCC • MR • OUT
AEC	MAX6406BS28	MAX	vd	V _{TR} =2.80B; V _{DO} =1.25.5B; I _{CC} <1.75 мкА	UCSP-4	GND • VCC • MR • OUT
AED	MAX6406BS29	MAX	vd	V _{TR} = 2.93B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AEE	MAX6406BS30	MAX	vd	V _{IR} =3.00B; V _{DD} =1.25.5B; I _{CC} <1.75 мкА	UCSP-4	GND • VCC • MR • OUT
AEF	MAX6406BS31	MAX	vd	V _{TR} =3.08B; V _{DD} =1.25.5B; I _{CC} <1.75 mKA	UCSP-4	GND • VCC • MR • CUT
AEG	MAX6407BS22	MAX	vd	V _{IR} = 2.20B; V ₀₀ = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
AEH	MAX6407BS23	MAX	νd	V _{IR} =2.32B; V _{DO} =1.25.5B; I _{CC} <1.75 мкА	UCSP-4	GND • VCC • MR • CUT
ΑEI	MAX6407BS24	MAX	vd	V _{TR} = 2.40B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AEJ	MAX6407BS25	MAX	vd	V _{IR} =2.50B; V _{DO} =1.25.5B; I _{CC} <1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AEK	MAX6407BS26	MAX	vd	V _{TR} = 2.63B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AEL	MAX6407BS27	MAX	vd	V _{TB} = 2.70B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AEM	MAX6407BS28	MAX	vd	V _{IR} =2.80B; V _{DO} =1.25.5B; I _{CC} <1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AEN	MAX6407BS29	MAX	vd	V _{IB} = 2.93B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AEO	MAX6407BS30	MAX	vd	V _{TR} =3.00B; V _{DO} =1.25.5B; I _{CC} <1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AEP	MAX6407BS31	MAX	vd	V _{TB} = 3.08B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mrA	UCSP-4	GND • VCC • MR • CUT
AEQ	MAX6408BS22	MAX	vd	V _{TR} = 2.20B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
AER	MAX6408BS23	MAX	vd	V _{TB} = 2.32B; V _{DO} = 1.25.5B; I _{CC} < 1.75 MKA	UCSP-4	GND • VCC • MR • CUT
AES	MAX6408BS24	MAX	vd	V _{TB} = 2.40B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
0.00	MAX6408BS25	MAX	1390	V _{IB} = 2.50B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
10000	MAX6408BS26	MAX	28	V _{TB} = 2.63B; V _{DO} = 1.25.5B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • CUT
10000	MAX6408BS27	MAX	02.5	V _{IB} = 2.70B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA	120000	GND • VCC • MR • OUT
100	MAX6408BS28	MAX	333	V _{TB} = 2.80B; V _{DD} = 1.25.5B; I _{CC} < 1.75 mKA		GND • VCC • MR • CUT
	/\0.00000		70	THE ELECTION OF THE STREET	- NO.	0.10 1.00 - IMIT - 001

UCSP-4 UCSP-5 UCSP-6 WLCSP-5 WLCSP-6 WCSP-8













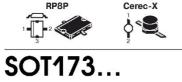


CSP-8	UCSP-9	UCSI
32 1	32 1 664	43 (6)
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Ф		Особенно



JUSP-1	
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Код	Типономинал	6	ф	Особенности	Корпус	Ц: 1•2•3•4••12
AEX	MAX6408BS29	MAX	vd	V _{TR} = 2.93 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 mKA	UCSP-4	GND • VCC • MR • OUT
AEY	MAX6408BS30	MAX	vd	V _{TR} = 3.00 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 мкА	UCSP-4	GND • VCC • MR • OUT
AEZ	MAX6408BS31	MAX	vd	V _{тR} = 3.08 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 мкА	UCSP-4	GND • VCC • MR • OUT
AFA	MAX6409BS33	MAX	vd	V _{TR} = 3.30 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 mkA	UCSP-4	GND ● VCC ● MR ● OUT
AFB	MAX6409BS34	MAX	vd	V _{TR} = 3.40 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 мкА	UCSP-4	GND • VCC • MR • OUT
AFC	MAX6409BS35	MAX	vd	V _{TR} = 3.50 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 мкА	UCSP-4	GND • VCC • MR • OUT
AFD	MAX6409BS36	MAX	vd	V _{TR} = 3.60 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 мкА	UCSP-4	GND • VCC • MR • OUT
AFE	MAX6409BS37	MAX	vd	V _{1R} = 3.70 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 мкА	UCSP-4	GND • VCC • MR • OUT
AFF	MAX6409BS38	MAX	vd	V _{TR} = 3.80 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 mkA	UCSP-4	GND • VCC • MR • OUT
AFG	MAX6409BS39	MAX	vd	V _{TR} = 3.90 B; V _{DO} = 1.25.5 B; I _{CC} < 1.75 mrA	UCSP-4	GND ● VCC ● MR ● OUT
AFH	MAX6409BS40	MAX	vd	V _{TR} = 4.00 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 мкА	UCSP-4	GND • VCC • MR • OUT
AFI	MAX6409BS41	MAX	vd	V _{TR} = 4.10 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 mrA	UCSP-4	GND • VCC • MR • OUT
AFJ	MAX6409BS42	MAX	vd	V _{TR} = 4.20 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 m/A	UCSP-4	GND • VCC • MR • OUT
AFK	MAX6409BS43	MAX	vd	V _{IR} = 4.30 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 мкА	UCSP-4	GND • VCC • MR • OUT
AFL	MAX6409BS44	MAX	vd	V _{TR} = 4.38 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 mrA	UCSP-4	GND • VCC • MR • OUT
AFM	MAX6409BS45	MAX	vd	V _{TR} = 4.50 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 mrA	UCSP-4	GND • VCC • MR • OUT
AFN	MAX6409BS46	MAX	vd	V _{TR} = 4.63 B; V _{DD} = 1.25.5 B; I _{CC} < 1.75 мкА	UCSP-4	GND • VCC • MR • OUT
ВЗА	AD8605ACB	AD	OA	$f_{BD} = 10 \text{ MFu}; P_D = 7 \text{ MBT}; V_{DD} = 2.75.5 \text{ B}$	WLCSP-5	OUT • V- • +IN • -IN • V+
CCS	OPA2347YED	П	dOA	R-R; V_{00} = 2.35.5 B; f_{80} = 350 kFu; I_S = 80 mkA; V_{OSI} < 7 mB	WCSP-8	OUT A • -IN A • +IN A • V - • +IN B • - IN B • OUT B • V+
SNB	ADG819BCB	AD	asw	SPDT; R _{ON} < 0.8 OM; V _{DD} = 1.85.5 B	WLCSP-6	S2 • D • S1 • GND • VDD • IN







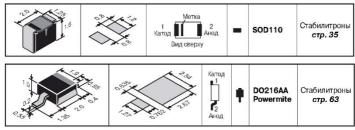


Код	Типономинал	Б	ф	Особенности	Корпус	Ц: 1•2•3•4
57	BFQ57	SIEM	npn	V _{CB0} = 25 B; I _C = 35 mA; P _D = 450 mBT	SOT-173	B•E•C•E
58	BFQ58	SIEM	npn	V _{CBO} = 16 B; I _C = 30 mA; P _D = 450 mBT	SOT-173	B•E•C•E
70	BFQ70	SIEM	npn	$V_{CB0} = 20 \text{ B; } I_C = 35 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} > 50; f_T = 5 \Gamma \Gamma \mu$	SOT-173	B•E•C•E
71	BFQ71	SIEM	npn	$V_{CB0} = 20 \text{ B; } I_C = 30 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} > 40; f_T = 5.2 \Gamma \Gamma_U$	SOT-173	B•E•C•E
72	BFQ72	SIEM	npn	$V_{CB0} = 20 \text{ B}; I_C = 50 \text{ mA}; P_D = 350 \text{ mBT}; h_{21} > 40; f_T = 5.1 \Gamma \Gamma_U$	SOT-173	B∙E∙C∙E
74	BFQ74	SIEM	npn	$V_{CB0} = 25 \text{ B; } I_C = 35 \text{ mA; } P_D = 300 \text{ mBT; } h_{21} > 50; f_T = 6 \Gamma \Gamma \mu$	SOT-173	B•E•C•E
75	BFQ75	SIEM	pnp	$V_{CB0} = 15 \text{ B; } I_C = 50 \text{ mA; } P_D = 350 \text{ mBT; } h_{21} > 20; f_T = 5 \Gamma \Gamma \mu$	SOT-173	B•E•C•E
76	BFQ76	SIEM	pnp	$V_{CB0} = 20 \text{ B}; I_C = 30 \text{ mA}; P_D = 250 \text{ mBT}; h_{21} > 20; f_T = 5 \Gamma \Gamma \mu$	SOT-173	B•E•C•E
77	BFQ77	SIEM	npn	$V_{CB0} = 25 \text{ B; } I_C = 20 \text{ mA; } P_D = 250 \text{ mBT; } f_T = 2 \Gamma\Gamma\text{LL}$	SOT-173	B•E•C•E
0	2SC3603	NEC	npn	$V_{CB0} = 20 \text{ B}; I_C = 100 \text{ mA}; P_D = 580 \text{ mB}_T; h_{21} = 50300; f_T = 7 \Gamma \Gamma \mu$	SOT-173	B•E•C•E
1	2SC3587	NEC	npn	$V_{CB0} = 20 \text{ B}; I_C = 35 \text{ mA}; P_D = 580 \text{ mB}\text{T}; h_{21} = 50250; f_T = 10 \Gamma\Gamma\text{L}$	SOT-173	B•E•C•E
32	BAT32	INF	shd	$V_R < 6.5B$; $I_F < 50 \text{ mA}$; $V_F (I_F = 10 \text{ mA}) < 0.6B$; $C_D = 0.24 \text{ n}\Phi$	Cerec-X	A∙K
674	NE67483B	NEC	nMESFET	GaAs;V _{DS} = 5 B; I _D = 120 mA; P _D = 270 mB t; g _F < 100 mCm	83B	S•D•S•G
73S	BFQ73S	SIEM	npn	$V_{CB0} = 20 \text{ B; } I_C = 100 \text{ mA; } P_D = 500 \text{ mBT; } h_{21} > 30; f_T = 5.3 \Gamma \Gamma_U$	SOT-173	B•E•C•E
C1	BFQ51C	PHIL	pnp	$V_{CB0} = 15 \text{ B}; I_C = 30 \text{ mA}; P_D = 250 \text{ mB}\tau; h_{21} > 20; f_T > 5 \Gamma \Gamma_U$	SOT-173	B•E•C•E
C2	BFQ32C	PHIL	рпр	$V_{CB0} = 15 \text{ B}; I_C = 100 \text{ mA}; P_D = 500 \text{ mBT}; h_{21} > 20; f_T > 4.5 \Gamma \Gamma \mu$	SOT-173	B•E•C•E
C3	BFQ23C	PHIL	рпр	$V_{CB0} = 15 \text{ B}; I_C = 50 \text{ mA}; P_D = 350 \text{ mBT}; h_{21} > 20; f_T > 5 \Gamma \Gamma_U$	SOT-173	B∙E∙C∙E
IX	2SK3390	REN	nMOS	V _{DS} = 17 B; I _D = 1 A; P _D = 20 B _T	RP8P	G•S•D
P0	BFP90A	PHIL	npn	V _{CB0} = 15 B; I _C = 80 mA; P _D = 350 mBT	SOT-173	B•E•C•E
P1	BFP91A	PHIL	npn	V _{CB0} = 15 B; I _C = 80 mA; P _D = 350 mB _T	SOT-173	B•E•C•E
P 6	BFP96	PHIL	npn	V _{CBD} = 20 B; I _C = 100 мA; P _D = 500 мВт; h ₂₁ > 25; f _T > 5ГГц	SOT-173	B•E•C•E

РАЗМЕРЫ КОРПУСОВ ДЛЯ ПОВЕРХНОСТНОГО МОНТАЖА

3 Man	1:1		BL	BW	ВН	PL
1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	-	0402 (1005)	1	0.5	0.350.55	0.2
	-	0603 (1608)	1.6	0.8	0.450.95	0.3
		0805 (2012)	2	1.2	0.41.6	0.5
		1206 (3216)	3.2	1.6	0.41.75	0.5
		1210 (3225)	3.2	2.5	0.551.9	0.5
Резисторы стр. 16		1218 (3245)	3.2	4.5	0.551.9	0.5
Кондесаторы стр. 17		1806 (4516)	4.5	1.6	1.6	0.5
Индуктивности		1808 (4520)	4.5	2	2	0.5
Термисторы		1812 (4532)	4.5	3.2	0.62.3	0.5
Варисторы		2010 (5025)	5	2.5	0.55	0.5
		2220 (5750)	5.7	5	1.7	0.5
		2225 (5763)	5.7	6.3	2	0.5
		2512 (6432)	6.4	3.2	2	0.5
		2824 (7161)	7.1	6.1	3.9	0.5
		3225 (8063)	8	6.3	3.2	0.5
		4030	10.2	7.6	3.9	0.5
		4032	10.2	8	3.2	0.5
		5040	12.7	10.2	4.8	0.5
		6054	15.2	13.7	4.8	0.5

							_				
- On	1:1	Тип	BL	BW	ВН	PB	PW	PH	SB	SL	SW
	-	SOD623	1.0	0.6	0.52	1.4	0.2	0.12			
	-	SOD723	1.0	0.6	0.52	1.4	0.29	0.1			
200	-	SOD523, SC79	1.2	8.0	0.6	1.6	0.3	0.14			
	-	SCD80	1.3	0.8	0.7	1.7	0.3	0.13	1.8	0.35	0.35
\$\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	-	DO219AB	2.8	1.8	1.0	3.7	1.0	0.16	4.2	1.3	1.4
on Man	1:1	Тип	BL	BW	ВН	РВ	PW	РН	SB	SL	sw
	-	ESC	1.2	0.8	0.6	1.6	0.3				
i i	-	SSC	1.3	0.8	0.8	2.1	0.3				
	-	SOD323, SC76	1.7	1.25	0.9	2.5	0.3	0.15	3.3	0.8	0.6
20		SOD123	2.7	1.55	1.35	3.2	0.6	0.15	4.19	0.91	1.22
E STAN		DO215AC	4.3	2.6	2.4	6.1	1.4				
		DO215AA	4.3	3.6	2.3	6.2	2.0	0.25			
/3		DO215BA	4.45	2.6	2.95	6.2	1.3				
~		DO215AB	6.85	5.9	2.3	9.9	3				
ar Man	1:1	Тип	BL	BW	ВН	PW	PH	РВ	SB	SL	sw
	-	2012 (0805)		1.2	1.2	1.1		2			
商	_	3216L 3216 (1206)		1.6	1.2 1.6	1.2		3.2			
		3528L 3528		2.8	1.2 1.9	2.2		3.5			
		DO214AC SMA	4.4	2.6	2.15	1.5	0.15	5.2	5.5	1.7	2
Sh. Ves		DO214BA		2.6	2.95	1.3		5.25			
		DO214AA SMB	4.4	3.6	2.2	2	0.2	5.4	6.1	2	2.5
		SOD6		3.8	2.5	2.2		5.5			
Кондесаторы стр. 17		5832		3.2	1.5	2.2		5.8			
Индуктивности стр. 18		5845		4.5	3.1	2.2		5.8			
Термисторы		6032		3.2	2.5	2.2		6			
Варисторы Диоды		7343 7343H		4.3	2.8 4.3	2.4		7.3			
Стабилитроны с тр. 35 (DO214)		SOD15		5	2.8	3		7.8			
стр. 63 (DO215) стр. 82 (DO219)		DO214AB, SMC	6.8	5.8	2.3	3	0.2	7.9	8.5	2.2	3.5



₹ \$	1:1	Тип корпуса	BL	BD	PL	PH	Источник
TX.	-	ERD03LL	1.6	1	0.2	0.05	PANASONIC
		ERO21L	2	1.25	0.3	0.07	PANASONIC
00 you		DO213AC	3.45	1.4	0.42	11=0	JEDEC
		SOD80, miniMELF	3.5	1.6	0.3	0.075	PHILIPS
		DO213AA, SOD80	3.5	1.65	0.48	0.03	JEDEC
-		SOD80C	3.6	1.52	0.3	0.075	PHILIPS
Резисторы <i>стр.</i> 8		SOD87	3.5	2.05	0.3	0.075	PHILIPS
Кондесаторы		MELF	5	2.5	0.5	0.1	CENTS
Диоды		DO213AB, MELF	5	2.52	0.48	0.03	JEDEC
Стабилитроны		ERSM	5.9	2.2	0.6	0.15	PANASONIC

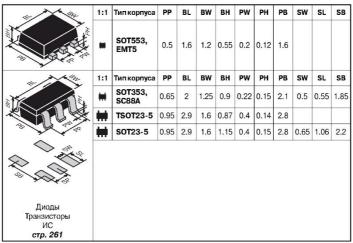
	2 1	-	TSLP-2	
	3 1 2	-	TSLP-3	. Диоды
	3 4 2 1	-	TSLP-4	Варикапы Транзисторы <i>стр. 88</i>
	456		μDFN-6	

SL S	SL	SL	SL		SW	PB	PH	PW	ВН	BW	BL	PP	Тип корпуса	1:1
				T		1.6	0.12	0.22	0.75	0.8	1.6	1	SOT523	+
0.65 1	0.65	0.65	0.65	. (0.4	1.6	0.15	0.2	0.75	0.8	1.6	1	SOT416, SC75A	÷
0.9	0.9	0.9	0.9	5	0.45	2.1	0.13	0.32	0.9	1.25	2	1.3	SOT323, SC70	•
						2.8	0.18	0.4	1	1.5	2.9	1.9	SOT346, SC59	÷
1.05 1	1.05	1.05	1.05	5	0.55	2.8	0.13	0.42	1.1	1.5	2.9	1.9	SOT23, SOD23	;
SL S	SL	SL	SL	1	SW	РВ	PH	PW	вн	BW	BL	PP	Тип корпуса	1:1
						1.2	0.15	0.2	0.53	0.8	1.2	8.0	TSFP-3, VESM	•
				T		1.2	0.13	0.22*	0.5	0.8	1.2	8.0	VMT3, VMD3	•
0.5 0	0.5	0.5	0.5	5	0.35	1.2	0.13	0.22	0.57	0.8	1.4	0.9	SC81, MFPAK	144
						1.2	0.14	0.22	0.59	8.0	1.4	0.9	TESM	-
				Ī		1.6	0.15	0.28	0.7	0.85	1.6	1	SOT490, SC89	*
			_			1.6	0.15	0.28	0.7	0.85	1000			

Схемы сброса стр. 90

	4 3 2 1 Вид сверху	SOT89, SC62	
	4 3 2	SOT223, TO261AA	Диоды Стабилитроны
	1 3	TO252, DPAK	Транзисторы Стабилизаторы Мониторы Схемы сброса АЦП <i>стр. 229</i>
	1 2 3	TO263, D2PAK	

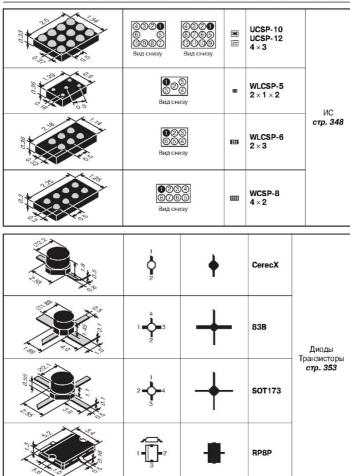
on on	1:1	Тип корпуса	PP	BL	BW	вн	PW	PH	РВ	SW	SL	SB
3	-	TSFP-4	1	1.4	0.8	0.55	0.2	0.15	1.2			
S A		MFPAK-4	1.3*	2	1.25	0.59	0.3*	0.11	2.05			
	* Для	вывода 2: PW	= 0.4	, PP =	1.25							
7000 NO BI	1:1	Тип корпуса	PP	BL	BW	вн	PW	PH	РВ	sw	SL	SB
200		SC82, USQ	1.3	2	1.25	0.95	0.2	0.15	2.1			
	#	SOT343, SC82A	1.3 ¹⁾	2	1.25	1	0.31)	0.12	2	0.51)	0.55	1.85
		SOT343R	1.31)	2	1.25	1	0.31)	0.12	2	0.51)	0.55	1.85
" \	#	MW-4	1.32)	2.9	1.3	1	0.42)	0.12	2.6			
\wedge	H	SOT143, TO253	1.9	2.9	1.3	1	0.43)	0.1	2.5	0.53)	0.6	1.9
XXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXXX		SOT143R	1.9	2.9	1.3	1	0.43)	0.1	2.5	0.53)	0.6	1.9
% \ /\$	Ħ	SC61, MPAK-4	1.9	2.9	1.5	1.1	0.44)	0.16	2.95)			
Диоды Варикапы Транзисторы ИС стр. 244	²⁾ Для ³⁾ Для ⁴⁾ Для	вывода 1: PW выводов 1 и ч вывода 1: PW вывода 4: PW оды имеют раз	4: PW / = 0.8 / = 0.6	= 0.7, , SW	PP= = 0.9	1.15		3 1, 2	4 0.85	для в	ыводо	эв 3, 4



84 Su	1:1	Тип корпуса	PP	BL	BW	вн	PW	PH	РВ	sw	SL	SB
£ 15		fS6	0.35	1	0.8	0.48	0.15	0.1	1			
	**	M16, 1208	0.4	1.2	8.0	0.5	0.15	0.125	1			
	***	USM-6	0.48	1.5	1.1	0.55	0.2	0.11	1.5			
, ×	-	SOT666	0.5	1.6	1.2	0.55	0.2	0.12	1.6	0.4	0.5	1.7
ROOF TO SERVICE STATE OF THE PERSON OF THE P	***	SOT563, EMT6	0.5	1.6	1.2	0.55	0.22	0.12	1.6			
		SON-6	0.5	1.6	2.6	0.8	0.2	0.13	3			
in the	1:1	Тип корпуса	PP	BL	BW	ВН	PW	PH	РВ	SW	SL	SB
	**	TSOT363	0.65	2	1.25	0.6	0.22	0.13	2.1			
WATER TO THE REAL PROPERTY OF THE PERTY OF T	***	SOT363, SC88	0.65	2	1.25	0.9	0.22	0.15	2.1	0.3	0.7	1.6
20 10 10	**	MW-6	0.95	2.9	1.3	1	0.3*	0.12	2.6			
	***	SOT457, SC74	0.95	2.9	1.6	1	0.35	0.15	2.5	0.5	0.5	2.4
\$, Q	-	TSOT23-6	0.95	2.9	1.6	0.88	0.4	0.18	2.75			
* 1023	**	SOT23-6	0.95	2.9	1.6	1.15	0.4	0.15	2.8	0.65	1.06	2.2
Диоды, Транзисторы, ИС <i>стр. 285</i>	* Для	вывода 5: PW	= 0.6									

		US-8 VSSOP-8 SOT765	
	***	SOT23-8	
Hiller to	##	MSOP-8	Транзисторы ИС <i>стр. 325</i>
THE TO SEE STATE OF THE PARTY O	 	MSOP-10	
		SOP-8	

<u>5</u> 678 432 1 Вид снизу		ML	P832-8		
5.67.8 432 1 Вид снизу		LFC	CSP-8		
678918 5432 1 Вид снизу		LFC	CSP-10		
678 321 Вид снизу		TDI	FN-6	Транзисторы ИС <i>стр. 345</i>	î.
5678 432 1 Вид снизу		TDFN-8			
67890 5432 0 Вид снизу		TO	FN-10, FN-10		
7/8/9 6 10 5 11 4 12 3/2 11 Видснизу		TQI	FN-12		
② ① ③ ④ Вид снизу		Ħ	UCSP-4 2×2		
③② ●	00	33 ⊞	UCSP-5 UCSP-6 3×2	ИС стр. 348	3
32 0 02 4 8 65 560 96 Вид снизу Вид с) <u>@</u>		UCSP-8 UCSP-9 3×3		



СПИСОК ФИРМ-ПРОИЗВОДИТЕЛЕЙ

Сокра- щение	Полное название фирмы
8X8	8x8, Inc.
ACAP	Acapella, Ltd.
ACC	ACC Microelectronics Corp.
ACCUL	Acculin, Inc.
ACTEL	Actel Corporation
AD	Analog Devices
ADAP	Adaptec
AEROF	Aeroflex Circuit Technology
AGI	Agilent
AHA	Advanced Hardware Architectures, Inc.
AIT	AlTech International
AKM	AKM Semiconductor, Inc.
ALD	Advanced Linear Devices
ALLEG	Allegro Micro Systems, Inc.
ALLIA	Alliance Semiconductor
ALPHA	Alpha Semiconductor
ALT	AverLogic Technologies, Inc.
ALTER	Altera Corporation
AMC	Accutek Microcircuit Corporation
AMCC	AMCC (Applied Micro Circuits Corp)
AMD	Advanced Micro Devices, Inc.
AMI	American Microsystems, Inc.
AMS	Applied Microsystems Corporation
AMSI	Austria Mikro Systeme International, Inc.
ANAD	Anadigics, Inc.
ANALO	Analogic Corporation
APEX	Apex Microtechnology Corporation
APTEK	Aptek Williams, Inc.
APTOS	Aptos Semiconductor Corporation
ARRAY	Array Microsystems
AS	Analog Systems
ASHL	Ashling Microsystems Ltd
ASPEC	Aspec Technology, Inc.
ASTEC	Astec Semiconductor
ATMEL	ATMEL Corporation
AUK	AUK Semiconductor
AUST	Austin Semiconductor, Inc.
AVG	AVG Semiconductors
AVX	AVX KYOCERA
BB	BurrBrown Corporation
BEL	Bel Fuse Incorporated
BENCH	Benchmarq Microelectronics
BOUR	BOURNS
BROOK	Brooktree Corporation
BUTT	ButterflyDSP,Inc.
C&T	Chips and Technologies, Incorporated
CALOG	Calogic Corporation
CATAL	Catalyst Semiconductor

Сокра- щение	Полное название фирмы
CCD	Cologne Chip Designs
CDIL	CDIL
CEC	Chip Express Corporation
CENTO	Centon Electronics, Inc.
CENTU	Century Microelectronics, Inc.
CERM	Cermetek Microelectronics, Inc.
CHERR	Cherry Semiconductor Corporation
CHRON	Chrontel
CL	Cirrus Logic, Inc.
CMDC	California Micro Devices Corporation
CML	Consumer Microcircuits Limited
CNTRL	Central Semiconductor
COLOR	Colorado Microcircuits
COMC	Comcore Semiconductor
COML	Comlinear Corporation
CONV	Conversion Devices, Inc.
CPC	CP Clare Corporation
CPS	Crosspoint Solutions, Inc.
CROSS	Crosslink Semiconductor, Inc.
CRYST	Crystal
CSC	Central Semiconductor Corp
CSI	Central Semiconductor, Inc.
CTC	стс
CYBER	Cybernetic Micro Systems
CYPR	Cypress Semiconductor Corp.
CYRIX	Cyrix Corporation
CYS	CYStech Electronic Corporation
DALL	Dallas Semiconductor
DALSA	Dalsa Incorporated
DATEL	Datel, Inc.
DDD	Data Delay Devices, Inc.
DENSE	DensePac Microsystems, Inc.
DIGIT	Digital Semiconductor
DIODS	Diodes Incorporeted
DION	Dionics Inc.
DIOT	Diotec Semiconductor
DSPG	DSP Group, Inc.
EDGE	Edge Technology, Inc.
EDI	Electronic Designs Inc.
EG&GI	EG&G IC Sensors
EG&GR	EG&G Reticon Corporation
ELANT	Elantec, Inc.
ELET	Eletech Electronics
ELMOS	Elmos Elektronik in MOSTechnologie GmbH
ELNA	ELNA
EMBED	Embedded Support Tools Corp.
EMM	EM Microelectronics
EMS	Enhanced Memory Systems, Inc.

Список фирм-производителей

Сокра- щение	Полное название фирмы
EMUL	Emulation Technology, Inc.
ENABL	Enable Semiconductor, Inc.
EPSON	Epson America Inc.
ERIC	Ericsson Components
ESC	ESC Electronics Corporation
ESS	ESS Technology, Inc.
ETC	Electronic Technology Corporation
EUROM	Eurom Ltd.
EXAR	Exar Corporation
EXEL	EXEL Microelectronics, Inc.
EXPO	Exponential Technology, Inc.
FAIR	Fairchild Semiconductor
UJIT	Fujitsu Microelectronics, Inc.
GALIL	Galileo Technology
GENES	Genesis Microchip Inc.
GENN	Gennum Corporation
GETE	GET Engineering Corp.
GLINK	GLink Technology Corporation
GOAL	Goal Electronics Inc.
GREEN	Greenwich Instruments USA
3S	General Semiconductor
GS	GSI Technology
HARR	Harris Corporation
HIFN	Hifn
HIT	Hitachi Semiconductor (America), Inc.
HOLT	Holt Integrated Circuits, Inc.
HOLTE	Holtek Microelectronics Inc.
HONEY	Honeywell Solid State Electronics Ctr.
HP.	HewlettPackard Logic Systems Division
HUAL	Hualon Microelectronics Corp
HUGH	Hughes Aircraft Co.
HUNT	Huntsville Microsystems, Inc.
-IYU	Hyundai Electronics America
BM	IBM Corporation
CH	IC Haus
CS	Integrated Circuit Systems, Inc.
CT	ICT Inc
CW	IC Works, Inc.
DC	IDC Semiconductors
DEAL	Ideal Semiconductor
DT	Integrated Device Technology, Inc.
LC	ILC Data Device Corp.
LS	Integrated Logic Systems Inc.
M	International Microcircuits, Inc.
MP	IMP, Inc.
MPAL	Impala Linear Corporation
NF	Infineon
NTEL	Intel Corporation

Сокра- щение	Полное название фирмы
INTRO	Intronics, Inc.
10	Otech, Inc.
IPC	Interpoint Corporation
IR	International Rectifier Corp.
ISD	Information Storage Devices, Inc
ISOC	Isocom Incorporated
ISS	Integrated Silicon Solution Inc.
IST	International Semiconductor Technologies
ITI	Interface Technology, Inc.
ITT	ITT Semiconductor
ITTI	Integrated Telecom Technology, Inc.
IXYS	IXYS Corporation
JGD	Japan Gude Electronic Devices
KAWAS	Kawasaki LSI, USA
KEC	Korean Electr. Corp.
KEMET	KEMET
KRUE	Krueger Company
LAMBD	Lambda Advanced Analog
LANSD	Lansdale Semiconductor, Inc.
LATT	Lattice Semiconductor Corp.
LD	Logic Devices Inc.
LECRO	LeCroy Corporation
LEVEL	Level One
LG	LG Semicon Company, Ltd.
LINF	Linfinity Microelectronics
LINT	Lintel Security S.A.
LIS	Linear Integrated Systems
LM	Lockheed Martin
LRC	Leshan Radio Company, Ltd.
LSIC	LSI Computer Systems, Inc.
LSIL	LSI Logic Corporation
LT	Linear Technology Corporation
LUC	Lucent Technologies Inc.
M/A	M/A-COM, Inc.
MALL	Mallory
MARV	Marvell Semiconductor, Inc.
MATRA	Matra MHS, Inc.
MATS	Matsuo
MAX	Maxim Integrated Products
MC	Mini-Circuits
MCC	Micro Commercial Components
MCHIP	Microchip Technology, Inc.
MCS	Microsemi
MICR	Micrel
MICRO	Microtek International, Inc.
MII	Micropac Industries, Inc.
MISI	Micronix Integrated Systems, Inc.
MITEL	Mitel Semiconductor

Список фирм-производителей

Сокра- щение	Полное название фирмы
MITS	Mitsubishi Electronics America, Inc.
ML	Micro Linear
MLINK	MetaLink Corporation
MNC	Micro Networks Company
MOSA	Mosaic Semiconductor, Inc.
MOSEL	MoselVitelic
MOSYS	MOSYS
MOT	Motorola Semiconductor Products
MPSC	MagePOWER Semiconductor Corporation
MR	MicroRel
MSIC	Mixed Signal Integration Corporation
MSIS	MSIS Semiconductor, Incorporated
MTI	Micron Technology, Inc.
MUR	Murata
MUSIC	Music Semiconductors, Inc.
MXC	MXCOM, Inc.
NACC	NACC
NANO	Nanoteq (Pty) Ltd
Nat	National Semiconductor
NCM	NCM Corporation
NEC	NEC Electronics Inc.
NEWP	Newport Components Limited
NEXC	Nexcom Technology, Inc.
NI	National Instruments
NJR	NJR Corporation
NOHAU	Nohau Corporation
NOVER	Nover
NPC	Nippon Precision Circuits Ltd.
NPNX	NPNX Corporation
N\$	National Semiconductor Corporation
NTE	NTE Electronics, Inc.
OAK	Oak Technology, Inc.
OEI	Optical Electronics Inc.
OKI	OKI Semiconductor, Inc.
ON	ON Semiconductors
ONCH	OnChip Systems, Inc.
OPTEK	Optek Technology, Inc.
OPTI	OPTi Inc.
OPTO	Optotek Limited
ORBIT	Orbit Semiconductor Inc.
ORION	Orion Instruments, Inc.
OXFOR	Oxford Micro Device, Inc.
PAN	Panasonic Industrial Company/Electronic Comp
PANJIT	Panjit Semiconductor
PARAD	Paradigm Technology, Inc.
PCA	PCA Electronics Inc.
PCC	Power Convertibles Corporation
PECG	Philips ECG

Сокра- щение	Полное название фирмы
PEPS	Performance Electronic Packaging Services
PERIC	Pericom Semiconductor Corporation
PHIL	Philips Semiconductors
PHYLO	Phylon Inc.
PI	Power Integrations, Inc.
PLESS	GEC Plessey Semiconductors
PLX	PLX Technology, Inc.
PMCS	PMCSierra
PMD	Performance Motion Devices, Inc.
PSC	Performance Semiconductor Corp.
PT	Power Trends
QLC	QuickLogic Corp
QLOG	QLogic Corporation
QS	Quality Semiconductor
QUALC	Qualcomm Incorporated
R&E	R&E International, Inc
RAMTR	Ramtron Corporation
RAYTH	Raytheon Company
REALT	Realtek Semiconductor Corporation
REN	Renesas
RFM	RF Micro Devices
RICOH	Ricoh Corporation
RMV	RMV Electronics Inc.
ROCH	Rochester Electronics Incorporated
ROCK	Rockwell Semiconductor Systems
ROHM	ROHM Corporation
S+M	Siemens Matsushita Components.
SAMS	Samsung Semiconductor, Inc.
SANYO	Sanyo Semiconductor Corporation
SCI	Silicon Composers, Inc.
SEEQ	SEEQ Technology, Incorporated
SEI	Space Electronics Incorporated
SEIKO	Seiko Instruments USA, Inc.
SEMT	Semtech Corporation
SENS	Sensory, Inc.
SEPON	Seponix Corporation
SGS	SGS-Thompson
SHARP	Sharp Electronics Corporation
SIEM	Siemens Microelectronics Inc.
SIGN	Signum Systems
SIL	Vishay Siliconix
SILIC	Silicom Inc.
SIMT	Simtek Corporation
SINC	Sincera
SIPEX	Sipex Corporation
SIS	SIS Microelectronics, Inc.
SMC	Standard Microsystems Corporation
SMOS	SMOS Systems, Inc.

Список фирм-производителей

Сокра- щение	Полное название фирмы				
SMS	Samsung Microwave Semiconductor, Inc.				
SOFT	Soft Device				
SOLIT	Solitron Devices, Inc.				
SONY	Sony Semiconductor Company of America				
SOUTH	South African MicroElectronic Systems (Pty)				
SPACE	Space Research Technology, Inc.				
SPT	Signal Processing Technologies				
SS	Silicon Systems Inc.				
SST	Silicon Storage Technology, Inc.				
STANF	Stanford Telecommunications Inc.				
STM	ST Microelectronics, Inc.				
SUMIT	Sumitomo Metal Industries, Ltd.				
SUN	Sun Microsystems, Inc.				
SUPER	Supertex, Inc.				
SYFER	Syfer				
SYMB	Symbios Logic				
SYNER	Synergy Semiconductor Corporation				
SYNT	Syntag Technology Inc.				
SYSTR	Systronix. Inc.				
TDK	TDK Semiconductor Corp.				
TECH	Technitrol Pulse Components Div.				
TELC	TelCom Semiconductor				
TELEF	Vishay Telefunken				
TELT	Teltone Corporation				
TEMIC	Temic Semiconductors				
Tfk	Telefunken (Vishay-Telefunken)				
THAL	Thaler Corp				
THAT	THAT Corporation				
THES	Thesys Gesellschaft fur Mikroelektronik mbH				
THIRD	Third Domain, Inc.				
THOMS	Thomson Components and Tubes Corporation				
TI	Texas Instruments, Inc.				
TLSI	TLSI Incorporated				
Tok	Toko Inc.				
ТОКО	Toko America Incorporated				
TOSH	Toshiba America Electronic Components, Inc.				
TRANS	TranSwitch Corporation				
TRID	Trident Microsystems Incorporated				
TRIQ	TriQuint Semiconductor				
TRITE	TriTech Microelectronics				

Сокра- щение	Полное название фирмы			
TSC	Taiwan Semiconductor			
TSENG	Tseng Labs, Inc.			
TSQW	Tsqware, Inc.			
TUNDR	Tundra Semiconductor Corporation			
TURBO	Turbo IC, Inc.			
UMC	United Microelectronics Corporation			
UNITR	Unitrode Integrated Circuits Corp.			
UNIV	Universal Semiconductor Inc.			
US M	US MikroChips, Inc.			
USAR	USAR Systems, Inc.			
UTM	United Technologies Microelectronics Center			
V3	V3 Semiconductor			
VADEM	Vadem			
VANT	Vantis Corporation			
VETRA	Vetra Systems Corporation			
VIA	VIA Technologies, Inc			
VIS	Vishay Semiconductors (Gen Semi, Tfk, Sil etc)			
VISH	Lite On (Vishay Lite On)			
VITES	Vitesse Semiconductor Corp.			
VITR	Vitramon			
VLSI	VLSI Technology Inc.			
VORT	Vortex Incorporated			
VTC	VTC Inc.			
WAFER	Waferscale Integration Inc.			
WD	Western Digital Corporation			
WDC	The Western Design Center, Inc.			
WEIT	Weitron			
WELTR	Weltrend			
WHITE	White Microelectronics			
WINB	Winbond Electronics Corp			
WOLF	Wolfson Microelectronics			
WTE	WTE Power Semiconductors			
XECOM	Xecom, Inc.			
XICOR	Xicor, Inc.			
XILIN	Xilinx Corp.			
YAGEO	Yageo			
YAMA	Yamaha Corp of America			
ZAXT	Zaxtek, Inc.			
ZETEX	Zetex			
ZOWIE	Zowie Technology Corporation			

СПИСОК СОКРАЩЕНИЙ И УСЛОВНЫХ ОБОЗНАЧЕНИЙ

			PLIPO TUD BORUSIOUSU
-	— вывод отсутствует	n.c. out	— вывод не подключен — выход
Α	— анод	pd	 несимметричный динистор для защиты обо-
a	 соединено с анодом 	μu	рудования связи
ACC	— погрешность	P_D	 рассеиваемая мощность
В	— база	R ₂₅	 сопротивление температурного датчика
C	— коллектор	R _{DS(on)}	 сопротивление канала в открытом состоянии
C _{10 B}	 емкость при напряжении на варикале 10 В 	**0S(on)	 сопротивление канала в открытом состоянии сопротивление ключа в открытом состоянии
C _{25 B}	 емкость при напряжении на варикале 25 В 	R _{ON} R-R	— вход/выход полного размаха (rail-to-rail)
C _{2B}	 емкость при напряжении на варикапе 2 В 	Rz	— динамическое сопротивление
C_{2B}/C_{30}	_в — отношение емкостей для различных напря-	S	— динамическое сопротивление — исток
	жений	Si	— кремний
ca	 с общим анодом 	substr	— подложка
CC	 с общим катодом 		 температура скружающей среды
CD	емкость диода	TAMB	 температурный коэффициент выходного на-
CISS	 входная емкость полевого транзистора 	TC _{VOUT}	пряжения
Com	— общий	TC _{VZ}	— температурный коэффициент напряжения
comp	 комплиментарный 	TOVZ	стабилизации
C _T	 суммарная емкость 		
D	— CTOK	t _{OFF}	— время выключения
DD	 динамический диапазон 	t _{PD}	— задержка переключения
DT	— рабочий цикл	t _{RES}	 длительность сброса
E	— эмиттер	t _{RR}	 время обратного восстановления
f _{BO}	 ширина полосы пропускания 	t _{STUP}	— задержка включения
f _{CLK}	— тактовая частота	TH	 температурный порог срабатывания
f _{DR}	 скорость передачи данных 	THAC	 точность температурного порога срабатыва-
f_{IN}	 входная частота 	т.	ния
fosc	 частота генератора 	THL	 нижний температурный порог срабатывания
f _P	 рабочая частота 	T _{THU}	 верхний температурный порог срабатывания
f _T	 граничная частота 	V _{BR}	— напряжение пробоя
fug	 частота единичного усиления 	VBROSS	— напряжение пробоя сток-исток
G	 затвор/управляющий электрод 	Vc	 напряжение фиксации (коллектора)
Gain	 коэффициент усиления 	V_{CB}	— пороговое напряжение circuit-breaker
g _F	 прямая проводимость полевого транзистора 	17	thresholds
GMA	 коэффициент усиления мощности 	V _{CB0}	 постоянное напряжение коллектор — база
gnd	— земля	Vcc	 положительное напряжение питания
h_{21}	 статический коэффициент передачи тока 	V _{CE(sat)}	 напряжение насыщения коллектор — эмит-
i.c.	 вывод внутренне подключен (не подсоеди- 	W	тер
	нять к внешней точке)	V _{CE0}	 постоянное напряжение коллектор эмиттер
IC	 ток коллектора 	V _{DS}	напряжение сток — исток
CAT	— ток катода	V _F	 прямое напряжение
I _{CB0}	 обратный ток перехода коллектор — база 	V _{GS}	 напряжение затвор — исток
I _{CH}	 ток заряда батареи 	V _{GSS}	 напряжение пробоя затвор исток
l _D	— ток стока	V _{GSTH}	 пороговое напряжение на затворе
loss	 ток стока при нулевом потенциале на затворе 	V _{OD}	 дифференциальное выходное напряжение
l _F	прямой ток	VoH	 выходное напряжение высокого уровня
l _G	— ток затвора	VOL	 выходное напряжение низкого уровня
leak	— ток утечки	Vosi	 напряжение смещения
in	— вход	Vout	— выходное напряжение
l _{PP}	 пиковый импульсный ток разряда 	V _B	 обратное напряжение
l _R	 обратный ток 	V _{REF}	— опорное напряжение
T	 средний ток в состоянии включения 	V _{TR}	 пороговое напряжение срабатывания
Iz	 ток стабилизации 	V _{THOV}	 порог превышения допустимого напряжения
I_{ZM}	 максимальный ток стабилизации 	V _{WW}	— напряжение выключения
ZT	 ток стабилизации в контрольной точке 	V_Z	 напряжение стабилизации
ĸ.	— катод	X	 безразличное состояние
k	 соединено с катодом 	Z_z	 дифференциальное сопротивление
LT	 — суммарная индуктивность 	Z_{ZT}	 дифференциальное сопротивление в конт-
max	— максимальное значение		рольной точке
min	 минимальное значение 		

СПИСОК ОБОЗНАЧЕНИЙ ФУНКЦИИ ПРИБОРА

2-AND — 2-входовый вентиль И	levtrans — преобразователь уровней логических сигналов
2-NAND — 2-входовый вентиль И-НЕ	ltcmp — компаратор локальной температуры
2-NOR — 2-входовый вентиль ИЛИ-НЕ	LVDSdrv — LVDS-драйвер линии
3-stbuff — неинвертирующий буфер с тремя состониями	mmic — СВЧ-микросхема
авс — контроллер тока смещения	mrc — схема сброса для микропроцессора
	nFET — n-канальный полевой транзистор с управля-
ADC — аналого-цифровой преобразователь	ющим <i>p-n-</i> переходом
amp — усилитель	nMESFET — n-канальный полевой транзистор с барье-
amux — аналоговый мультиплексор	ром Шоттки на основе GaAs
asw — аналоговый ключ	nMOS — n-канальный МОП-транзистор
ats — аналоговый температурный датчик	npn — <i>n-p-n</i> -транзистор
atten — аттенюатор	0 — однопереходный транзистор
batprot — схема защиты литиевых аккумуляторов	ОА — операционный усилитель
bcontr — контроллер для повышающих dc-dc-преоб-	PD — детектор ВЧ-сигнала
разователей	pd — несимметричный динистор для защиты обо-
btd — динистор	рудования связи
buf — буфер	pFET — p-канальный полевой транзистор с управля-
byd — быстрый выпрямительный диод с «мягким»	ющим р-п-переходом
восстановлением	pin — <i>p-i-n-</i> диод
byg — быстрый высоковольный выпрямительный	pMOS — p-канальный МОП-транзистор
диод с «мягким» восстановлением	рпр — р-п-р-транзистор
byh — выпрямительный диод общего применения	pnpn — программируемый однопереходной тран-
byv — высоковольтный выпрямительный диод	
cld — стабилизатор тока	3UCTOP
chg — контроллер зарядного устройства для акку-	prot — микросхема защиты аналоговых входов
муляторов	PWM — ШИМ-контроллер для изолированных источ-
стр — компаратор	ников питания
cpin — переключательный pin-диод	рг — защитный стабилитрон
cpreg — стабилизатор напряжения с накачкой заряда	rec — приемник
CSA — токовый усилитель	reg+mrc — стабилизатор напряжения со схемой сброса
d — диод (сборка)	для микропроцессора
DA — дифференциальный усилитель	reg — стабилизатор напряжения
DAC — цифро-аналоговый преобразователь	reg- — стабилизатор отрицательного напряжения
dcdc — DC/DC-преобразователь	reg+ — стабилизатор положительного напряжения
di — импульсный диод	rts — резистивный температурный датчик
dih — импульсный диод с большим рабочим током	Schminv — инвертор с триггером Шмитта на входе
 dl — диод общего применения с малым током утечки 	SchmNAND — 2-входовый вентиль И-НЕ с триггером
dnMESFET — n-канальный полевой транзистор с барье-	Шмитта на входе
ром Шоттки на основе GaAs с двумя затворами	scvcon — преобразователь напряжения на переключа-
ром Шоттки на основе GaAs с двумя затворами domixer — преобразователь-смеситель с понижением	scvcon — преобразователь напряжения на переключа- ющих конденсаторах
dnmixer — преобразователь-смеситель с понижением	
dnmixer — преобразователь-смеситель с понижением частоты сигнала	ющих конденсаторах
dnmixer — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" n-канальный МОП-транзистор	ющих конденсаторах sd — импульсный переключающий диод shd — диод Шоттки
dnnixer — преобразователь-смеситель с понижением частоты сигнала DnMOS — "чифоровой" п-канальный МОП-транзистор dnMOS — л-канальный МОП-транзистор с двумя за-	ющих конденсаторах sd — импульсный переключающий диод
dmixier — преобразователь-смеситель с понижением частоты сиптала DnMOS — "цифровой" п-канальный МОП-транаистор dmMOS — п-канальный МОП-транаистор с двумя за- творами	ющих конденсаторах sd — импульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связу.
dnmixer — преобразователь-смеситель с понижением частоть сигнала DnMOS — "цифровой" п-канальный МОП-транзистор dnMOS — л-канальный МОП-транзистор с двумя за- творами Dnpn — «цифровой» <i>п-р-п</i> -транзистор	ющих конденсаторах; sd — импульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — окиметричный динистор для защиты обору-
dimixier — преобразователь-смеситель с понижением частоты сигнала DnMOS — "шифровой" п-канальный МОП-транзистор dimOS — п-канальный МОП-транзистор с двумя за- творами Dnpn — «цифровой» п-р-л-транзистор dnpn — осогавной п-р-л-транзистор	ющих конденсаторах sd — импульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связу.
dimixer — преобразователь-смеситель с понижением частоты сигнала инальный МОП-транзистор dimMOS — л-канальный МОП-транзистор dimMOS — л-канальный МОП-транзистор с двумя затворами	ющих конденсаторах sd — милульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc-
dnmixer — преобразователь-смеситель с понижением частоть сигнала DnMOS — "ифоровой" п-канальный МОП-транзистор dnMOS — л-канальный МОП-транзистор с двумя затворами Dnpn — «цифровой» л-р-л-транзистор dnpn — составной л-р-л-транзистор dnpn — составной л-р-л-транзистор DpMOS — "цифровой" п-р-л-транзистор DpMOS — "цифровой" р-канальный МОП-транзистор DpMOS — "цифровой" р-канальный МОП-транзистор	ющих конденсаторах sd — импульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc- pm-pcoбразователей
dmnixer — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный МОП-транзистор dnMOS — п-канальный МОП-транзистор с двумя за- творами Dnpn — «цифровой» п-р-л-транзистор dnpn — осотавной п-р-л-транзистор dnpn — осотавной п-р-л-транзистор dOA — двуханальный операционный усилитель DpMOS — "цифровой" р-канальный МОП-транзистор Dpnp — «цифровой» при-транзистор	ющих конденсаторах sd — импульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc- преобразователей spz — симметричный защитный стабилитрон sw — переключатель (ключ)
dnmixer — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный МОП-транзистор dnMOS — л-канальный МОП-транзистор с двумя затворами Dnpn — «цифровой» п-р-л-транзистор dnpn — составной п-р-л-транзистор dOA — двужанальный попрационный усилитель DpMOS — "цифровой" р-канальный МОП-транзистор Dnp — «цифровой» прт-транзистор dnp — составной прп-транзистор	ющих конденсаторах sd — импульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc- преобразователей spz — симметричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель дребезга контактов
dmnixer — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный МОП-транзистор dmMOS — п-канальный МОП-транзистор с двумя затворами Dnpn — «цифровой» п-р-л-транзистор образовательный мОП-транзистор dnpn — составной п-р-л-транзистор dOA — двужанальный операционный усилитель DpMOS — "цифровой" р-канальный МОП-транзистор Dnpn — «цифровой» прп-транзистор dnpn — составной прп-транзистор Dpot — цифровой опенциометр	ющих конденсаторах sd — милульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc- пресобразователей spz — симметричный защитный стабилитрон sw — переключатель (ключ) sw — подавитель дребезга контактов tempsw — пороговый датчик температуры
dimixer — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный МОП-транзистор dnMOS — л-канальный МОП-транзистор с двумя за- творами Dnpn — «цифровой» п-р-п-транзистор dnpn — составной п-р-п-транзистор dnpn — составной п-р-п-транзистор долу прифровой п-р-канальный мОП-транзистор Dpn — «цифровой» р-канальный мОП-транзистор dnp — составной рпр-транзистор dpnp — составной рпр-транзистор Dpt — цифровой потенциометр dr — выпрымительный дмод	ющих конденсаторах sd — импульсный переключающий диод shd — диод Шоттки sty — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc- преобразователей spz — симметричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель дребезга контактов tempsw — пороговый датчик температуры trans — приемопередатчик
dmnixer — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный MOП-транзистор сілМОS — п-канальный MOП-транзистор с двумя затворами Dnpп — «цифровой» п-р-л-транзистор образовать продами Dnpп — составной п-р-л-транзистор образовать прифремей п-р-л-транзистор образовать прифремей п-р-л-транзистор образовать прифремей п-р-л-транзистор образовать прифремей при-транзистор образовать прифремей при-транзистор образовать прифремей примей прифремей прифремей прифремей прифр	ющих конденсаторах sd — милульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc- преобразователей spz — симметричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель дребезга контактов tempsw — пори свый датчик температуры transi — приемопередатчик transit — передатчик
diminizer — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный МОП-транзистор dimiNOS — п-канальный МОП-транзистор с двумя затворами Dnpn — «цифровой» п-р-п-транзистор с двумя затворами Dnpn — «цифровой» п-р-п-транзистор dnpn — составной п-р-п-транзистор dnpn— составной п-р-п-транзистор Dpm — чифровой» прп-транзистор Dpn — сифровой» прп-транзистор dnp — составной рnp-транзистор dnp — составной рnp-транзистор dnp — составной рnp-транзистор dn — выпрямительный диод dr — драйвер МОП-транзистора dr — выпрямительный диод dr — драйвер МОП-транзистора ds — цифровой ключ	ющих конденсаторах sd — импульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc- преобразователей spz — симметричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель дребезга контактов tempsw — пороговый датчик температуры trans — приемопередатчик trismit — передатчик TSPD — триристрный прибор защиты
dimixier — преобразователь-смеситель с понижением частоты сигнала DinMOS — "чифоровой" п-канальный MOП-транзистор dinMOS — п-канальный MOП-транзистор с двумя затворами Dinn — «цифоровой» п-р-л-транзистор двумя затворами Dinn — осотавной п-р-л-транзистор dinn — осотавной п-р-л-транзистор dinn — осотавной п-р-л-транзистор dinn — осотавной п-р-л-янальный мОП-транзистор DMOS — "цифоровой" ріпр-транзистор Dpn — «цифоровой» прп-транзистор dpn — осотавной ріпр-транзистор dpn — осотавной ріпр-транзистор dpn — осотавной ріпр-транзистор dpn — осотавной ріпр-транзистор drn — выпрямительный умод оти — драйвер МОП-транзистора dsw — цифоровой ключ dts — цифоровой на dts — ц	ющих конденсаторах sd — милульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc- просоразователей spz — симметричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель дребезга контактов tempsw — пороговый датчик температуры trans — приемопередатчик TSPD — тиристрный прибор защиты Upriliker — преобразователь-смеситель с повышением
dimixier — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный МОП-транзистор сілімОS — п-канальный МОП-транзистор сілімОS — п-канальный МОП-транзистор сілімОворами продами прода	ющих конденсаторах' sd — милульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc- пресбразователей spz — симметричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель дребезга контактов tenpsw — пороговый датчик температуры trans — приемопередатчик TSPD — тиристрный прибор защиты upniva — преобразоваталь-смеситель с повышением частоты силгала
dimixer — преобразователь-кмеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный МОП-транзистор dnMOS — л-канальный МОП-транзистор с двумя за- творами Dnpn — «цифровой» п-р-п-транзистор dnpn — составной п-р-п-транзистор dnp — составной п-р-п-транзистор dnp — составной п-р-п-транзистор двужанальный поерационный усилитель DpMOS — "цифровой" р-канальный МОП-транзистор Dpnp — «цифровой» пр-транзистор dpnp — составной рлр-транзистор dpnp — составной рлр-транзистор dpn — цифровой потенциометр dr — выпрямительный дмод cirv — драйвер МОП-транзистора dsw — цифровой ключ dts — цифровой температурный датчик dtv — диод для переключения дмапазонов телеви- зионного приемника	ющих конденсаторах sd — импульсный переключающий диод shd — диод Шоттки sty — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc- преобразователей spz — симметричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель дребеята контактов tempsw — пороговый датчик гемпературы trans — порисмонередатчик trasmit — передатчик TSPD — туристрный прибор защиты upmixer — преобразователь-смеситель с повышением частоты сигнала уа — варикап
dimixier — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный МОП-транзистор dim/OS — л-канальный МОП-транзистор с двумя затворами Dnpn — «цифровой» п-р-л-транзистор с двумя затворами Dnpn — «цифровой» п-р-л-транзистор dnpn — осотавной п-р-л-транзистор dnpn— осотавной п-р-л-транзистор двужанальный операционный усилитель DpMOS — "цифровой" р-канальный мОП-транзистор dnp — оситавной рпр - транзистор dnp — оситавной рпр - транзистор dnp — оситавной рпр - транзистор dr — выпрямительный диод dr — двифровой отогенциометр dr — выпрямительный диод dr — драйвер МОП-транзистора dsw — цифровой гыпоч образов и двительный двичик dtv — диод для переключения дмапазонов телевизисныго приемника dz — стабилитрон стабили	ющих конденсаторах' sd — милульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc- пресобразователей spz — симметричный защитный стабилитрон sw — переключатель (ключ) sw — подавитель деребата контактов tempsw — пороговый датчик температуры trans — приемопередатчик transit — передатчик TSPD — тиристрный прибор защиты upnixe — переобразователь-смеситель с повышением частоты синтала var — варижап vCO — генератор управляемый напряжением
diminizer — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный МОП-транзистор dimiNOS — п-канальный МОП-транзистор с двумя затворами Dnpn — «цифровой п-р-п-транзистор с двумя затворами Dnpn — «цифровой п-р-п-транзистор dnpn — составной п-р-п-транзистор dnpn — составной п-р-п-транзистор Dpm — чифровой п-р-канальный мОП-транзистор Dpn — сифровой п-р-пранзистор Dpn — сифровой потенциометр dr — выпрямительный диод drv — драйвер МОП-транзистор dr — выпрямительный диод drv — драйвер МОП-транзистор dsw — цифровой компературный датчик dtv — диод для переключения диапазонов телевизионного приемника dcz — стабилитрон dd — быстродействующий диод	ющих конденсаторах' sd — импульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc- преобразователей sp — симметричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель дребезга контактов tempsw — пороговый датчик температуры trans — присотрый прибор защиты traniii — передатчик TSPD — тиристрный прибор защиты upnixer — преобразователь-смеситель с повышением частоты сигнала var — варикая VCO — генератор управляемый напряжением vco — преобразователь напряжением
dmnixer — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный MOП-транзистор dmNOS — п-канальный MOП-транзистор с двумя затворами Dnpп — «цифровой» п-р-л-транзистор с двумя затворами Dnpп — «цифровой» п-р-л-транзистор dnpn — осотавной п-р-л-транзистор dnpn — осотавной п-р-л-транзистор dnpn — оставной п-р-л-транзистор DpnD — «цифровой» рпр-транзистор Dpn — чифровой» прп-транзистор dnp — осотавной п-р-л-транзистор dnp — осотавной п-р-пранзистор dr — выпрымительный диод dr — драйвер MOП-транзистора dsw — цифровой ключ — драйвер мОП-транзистора dsw — цифровой ключ — двифровой ключ dts — цифровой ключ dts — цифровой ключ dts — дифровой сминературный датчик dtv — дуод для переключения диапазонов телевизионного приемних dи дод fid — быстродействующий диод fid — быстродействующий импульсный диод fid — быстродействующий импульсный диод fid — быстродействующий импульсный диод	ющих конденсаторах' sd — милульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи spz — симметричный защитный стабилитрон spz — симметричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель дребезга контактов tempsw — приемопередатчик тязліт — приемопередатчик тязліт — передатчик тязліт — преобразователь-смеситель с повышением частоть сигнала var — варикап VCO — генератор управляемый напряжением vcon — пресобразователь напряжением vcon — пивертирующий пресобразователь напряже-
dimixier — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный МОП-транзистор сім МОП-транзистор сім МОП-транзистор сім МОП-транзистор сім МОП-транзистор сім могатично по пред могатично по премника сід стаби и по протрамника сід стаби и по	ющих конденсаторах' sd — импульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШММ-контроллер для понижающих dc-dc- преобразователей spz — симметричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель дребезга контактов tempsw — пороговый датчик температуры trans — приемопередатчик trismit — передатчик TSPD — тиристрный прибор защиты upnixer — преобразователь-смеситель с повышением частоты сингал var — варикап vCO — генератор управляемый напряжением vcor — инвертирующий преобразователь напряжения vcp — инвертирующий преобразователь напряжения vcp — инвертирующий преобразователь напряжения
dimixier — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный MOП-транзистор сімбОS — "канальный MOП-транзистор сімбОS — п-канальный MOП-транзистор сімбОS — п-канальный MOП-транзистор образовать продами Dnpп — «цифровой» п-р-л-транзистор образовать продами DnMOS — "цифоровой" р-р-л-транзистор образовать продами операционный усилитель DpMOS — "цифоровой» гірп-транзистор обрир — составной рпр-транзистор обрир — составной рпр-транзистор обрир — составной рпр-транзистор обрир — составной рпр-транзистор обрир — оставной рпр-транзистора образовом и прайзовать прайзо	ющих конденсаторах sd — милульсный переключающий диод shd — диод Шоттки shd — диод Шоттки spd — симметричный диид шоттки spz — симметричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель дребезга контактов tempsv — пороговый датичк температуры transt — приемопередатчик TSPD — тиристрный прибор защиты прийзет — преобразователь-смеситель с повышением частоты сигнала var — варикап VCO — генератор управляемый напряжением vcon — преобразователь напряжением vcon — преобразователь напряжением vcon — преобразователь напряжением vcon — инвертирующий преобразователь напряжение инв с накачкой заряда vd — монитор напряжения (
dimixier — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный МОП-транзистор сілМОS — п-канальный МОП-транзистор с двумя затворами Dnpn — «цифровой» п-р-л-транзистор с двумя затворами Dnpn — «цифровой» п-р-л-транзистор облем составной п-р-л-транзистор облем составной п-р-л-транзистор облем составной п-р-л-транзистор обрум — «цифровой» р-пр-транзистор обрум — систавной рпр-транзистор обрум — составной риод обруж — составной риод обруж — составной риод обруж — составилитром — составилительной риод — состави	ющих конденсаторах sd — милульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc- пресобразователей spz — симметричный защитный стабилитрон sw — переключатель (ключ) sw — подавитель дребезга контактов tempsw — пороговый датчик температуры trans — приемопередатчик transit — передатчик TSPD — тиристрный прибор защиты var — варижап var — варижап vco — генератор управляемый напряжением vcpcon — инвертирующий преобразователь напряжения vcp — инвертирующий преобразователь напряжения vd — монитор напряжения vcp — инвертирующий преобразователь напряжения vc — преобразователь напряжение vcp — инвертирующий преобразователь напряжение vcp — инвертирующий преобразователь напряжение vcp — vc — преобразователь напряжение vcp — преобразователь напряжение vcp — vc —
dimixier — преобразователь-смеситель с понижением частоты сигнала DnMOS — "шифровой" п-канальный МОП-транзистор сімбОS — "канальный МОП-транзистор сімбОS — "канальный МОП-транзистор сімбОS — п-канальный МОП-транзистор образовать продами Dnpп — «цифровой» п-р-л-транзистор образовать продами DnmOS — "шифоровой" р-р-л-транзистор образовать продами операционный усилитель рМОS — "шифоровой" рнр-транзистор обрр — осставной рир-транзистор обрр — осставной рир-транзистор обрр — осставной рир-транзистор обрр — осставной рир-транзистор оброжно оставной рир-транзистор оброжно образовать продавер мОП-транзистора образовать правов мопературный датчик обто — дифоровой ключ образовать продавер мОП-транзистора образовать продавер мОП-транзистора образовать продавилитрон образовать программируемый конденсатор обътродействующий импульсный диод обътродействую	іощих конденсаторах sd — милульсный переключающий диод shd — диод Шоттки shd — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи spz — симметричный динистор для защиты обору- дования связи spz — симметричный динистор для защиты обору- дования связи spz — симметричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель дребезга контактов tempsw — пороговый датчик температуры trans — приемопередатчик TSPD — тиристрный прибор защиты upnixer — преобразователь-смеситель с повышением частоты сигнала var — варикап VCO — генератор управляемый напряжением vcon — преобразователь напряжения vcon — преобразователь напряжения vcon — инвертирующий преобразователь напряжения vd — монитор напряжения (детектор напряжения) VFC — преобразователь напряжение- частоты сигнала vd — монитор напряжения (детектор напряжения) VFC — преобразователь напряжение- частота vd — монитор напряжения vd — монитор напряжения vd — монитор напряжения vd — монитор напряжения vd — драйвер виборозвонка
dimixier — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный MOП-транзистор dim/OS — л-канальный MOП-транзистор с двумя затворами Dnpn — «цифровой» п-р-л-транзистор с двумя затворами Dnpn — «цифровой» п-р-л-транзистор образовательный поперационный усилитель образовательный операционный усилитель образовательный операционный усилитель образовательный поперационетор образовательный потенциометор образовательный диод образовательн	ющих конденсаторах sd — милульсный переключающий диод shd — диод Шоттки sty — выпрямительный диод Шоттки sty — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи spz — симметричный динистор для защиты обору- дования связи spz — симметричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель дребезга контактов tempsw — пороговый датчик температуры trans — приемопередатчик TSPD — тиристрный прибор защиты upnixer — преобразователь-смеситель с повышением частоты сигнала va — варижал va — варижал va — варижал va — преобразователь напряжением vcco — преобразователь напряжением vcco — инвертирующий преобразователь напряжения vd — монтор напрежения vd — монтор напрежение vec — преобразователь напряжение vec — преобразователь vec — пр
diminizer — преобразователь-смеситель с понижением частоты сигная DinMOS — "чифоровой" п-канальный MOП-транзистор dinMOS — "чифоровой" п-канальный MOП-транзистор с двумя затворами Dinn — «цифоровой» п-р-л-транзистор с двумя затворами Dinn — «цифоровой» п-р-л-транзистор образовательный моперационный усилитель DinMOS — "цифоровой" регунальный МОП-транзистор DinD — «цифоровой» прр-транзистор обра — составной ригу-транзистор обра — составной ригу-транзистора обра — программируемый конденсатор объетровостанавливающийся выпрямительный ригус ден — программируемый генератор сигналов hscontr — контроллер "горячей замены" А — инструментальный усилитель	ющих конденсаторах я — умитульсный переключающий диод я на — диод Шоттки я на — выпрямительный диод Шоттки я на — выпрямительный диод Шоттки я на — комметричный динистор для защиты обору- дования связи ЯРМ — ШММ-контроллер для понижающих dc-dc- преобразователей я рас — симметричный защитный стабилитрон я м — переключатель (ключ) я м — подавитель дребезга контактов тепрям — пороговый датчик температуры таля — приемопередатчик тлятіт — передатчик ТРР — тиристрный прибор защиты црпікаг — преобразователь-смеситель с повышением частоты синтала уст — варикап усо — генератор управляемый напряжением усо — преобразователь напряжения уст — на с накачкой заряда уст — монитор напряжения уст — преобразователь напряжения уст — преобразователь напряжение уст — инектрующий преобразователь напряжения уст — преобразователь напряжением уст — преобразователь напряжения уст — правитель выбросов напряжения уст — правитель выбросов напряжения уст — источник опорног напряжения уст — источник опорног напряжения уст — правитель выбросов напряжения уст — правитель напряжения уст — правитель напряжения уст — правитель напряжения уст — правитель выбросов напряжения уст — правитель нап
dmnixer — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный MOП-транзистор dmNOS — п-канальный MOП-транзистор с двумя затворами Dnpп — «цифровой» п-р-п-транзистор с двумя затворами Dnpп — «цифровой» п-р-п-транзистор образовательный попрационный усилитель образовательный операционный усилитель образовательный попрационный усилитель образовательный диод образовательны	ющих конденсаторах sd — милульсный переключающий диод shd — диод Шоттки sty — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи spz — симметричный защитный стабилитрон spz — симметричный защитный стабилитрон sw — переключатель (ключ) sw — подавитель дребезга контактов tempsw — подоговый датчик температуры trans — приемопередатчик TSPD — тиристрный прибор защиты upnixer — преобразователь-смеситель с повышением частоты сигнала var — варикат vco — преобразователь напряжением vco — преобразователь напряжение vco — преобразователь напражение vco — преобразователь напражение vco — преобразователь напражение vco — преобраз
diminizer — преобразователь-смеситель с понижением мастоты сигнала DnMOS — "цифровой" п-канальный МОП-транзистор сілМОS — п-канальный МОП-транзистор сілМОS — п-канальный МОП-транзистор сілмОS — п-канальный МОП-транзистор сілр — составной п-р-л-транзистор сілр — составной п-р-л-транзистор сілр — составной п-р-л-транзистор сіле — составной п-р-л-транзистор сіле — составной п-р-л-пранзистор сіле — составной рор-транзистор сіле — составной рор-транзистор сіле — за прифровой п-р-л-ранзистор сіле — за пременальный диод сіле — драйвер МОП-транзистора сізе — цифровой ключ сіть — цифровой ключ сіть — цифровой ключ сіть — цифровой температурный датчик сіле — цифровой ключ сіть — цифровой ключ сіть — стабилитрон біть — программируємый клеценсатор біть — программируємый клеценсатор біть — контроллер "горячей замены" ім — инструментальный усилитель выми транзисторам на входе	ісцих конденсаторах' sd — милульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симметричный динистор для защиты обору- дования связи SPM — ШИМ-контроллер для понижающих dc-dc- преобразователей spz — симметричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель кребезга контактов tempsw — пороговый датчик температуры trans — приємопередатчик trsmit — передатчик TSPD — тиристріный прибор защиты upnixer — преобразователь-смеситель с повышением частоты синтала var — варижап vCO — генераттоу правляемый напряжением vcon — инвертирующий преобразователь напряжения vcon — инвертирующий преобразователь напряжения vcor — инвертирующий преобразователь напряжения vcor — преобразователь напряжение частота vibdry — драйвер виброзвонка vret — источник опорного напряжения vs — подавитель выбросов напряжения (супрессор) vse — монитор напряжения для приборов с двумя напряжением питания
dmnixer — преобразователь-смеситель с понижением частоты сигнала DnMOS — "цифровой" п-канальный MOП-транзистор dmNOS — п-канальный MOП-транзистор с двумя затворами Dnpп — «цифровой» п-р-п-транзистор с двумя затворами Dnpп — «цифровой» п-р-п-транзистор образовательный попрационный усилитель образовательный операционный усилитель образовательный попрационный усилитель образовательный диод образовательны	ющих конденсаторах sd — митульсный переключающий диод shd — диод Шоттки shy — выпрямительный диод Шоттки spd — симнетричный динистор для защиты обору- дования связи spz — симнетричный защитный стабилитрон spz — симнетричный защитный стабилитрон sw — переключатель (ключ) swd — подавитель дребезга контактов tempsw — порогосвый датчик температуры trans — приемопередатчик TSPD — тиристрный прибор защиты треобразователь-смеситель с повышением частоты сигнала var — варикат VCO — преобразователь напряжением vcocon — преобразователь напряжением vcocon — инвертирующий преобразователь напряжением vcocon — инвертирующий преобразователь напряжением vcocon — инвертирующий преобразователь напряжения vd — монитор напряжения (агектор напряжения) VFC — преобразователь напряжение vd — монитор напряжение veroun — инвертирующий преобразователь напряжения vd — монитор напряжение vero-чик спорного напряжения ver — источник спорного напряжения ver — подавитель выброзове напряжения ver — источник спорного напряжения ver — подавитель выброзове напряжения ver — источник спорного ver — исто

ТАБЛИЦА СООТВЕТСТВИЯ ОБОЗНАЧЕНИЙ НАИБОЛЕЕ ПОПУЛЯРНЫХ КОРПУСОВ

JEDEC	EIAJ	PHILIPS SIEMENS CENTS MAXIM	понм	SANYO	нітасні	MOTOROLA	TOSHIBA KEC
TO-236	SC-59	SOT-346	SMD/T3		MPAK2	SC-59	S-MINI
TO-236AB	SC-59A	SOT/SOD- 23	SSD/T3	СР	MPAK	SOT-23	
TO-243AA	SC-62	SOT-89A	мрт3	PCP	UPAK		PW-MINI
TO-243AB		SOT-89B					
TO-252-3	SC-63		СРТ3				
TO-253		SOT-143	SMD/T4			SOT-143	
TO-253		SOT-143R					
		SOD-123				SOD-123	
	SC-76	SOD-323	UMD2				USE
	SC-82A	SOT-343					
		SOT-343R			CMPAK-4		
		SOT-87					
	SC-70	SOT-323	UMD/T3	MCP	CMPAK	SOT-323	USM
	SC-74	SOT457	SMD/T6				SM6
	SC-74A	SOT23-5	SMD/T5				SMV
	SC-75A, SC90	SOT-416	EMD/T3	SMCP	SMPAK		SSM
	SC-79	SOD-523	EMD2				ESC
	SC-82	T	UMD/T4				USQ
	SC-88	SOT-363	UMD/T6				US6
	SC-88A	SOT-353	UMD/T5				USV
	SC61				MPAK-4		SMQ
	SC89	SOT490					ESM
			VMT3				USQ

